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(54) **INTEGRATED CIRCUIT CHIP USING TOP POST-PASSIVATION TECHNOLOGY AND BOTTOM STRUCTURE TECHNOLOGY**

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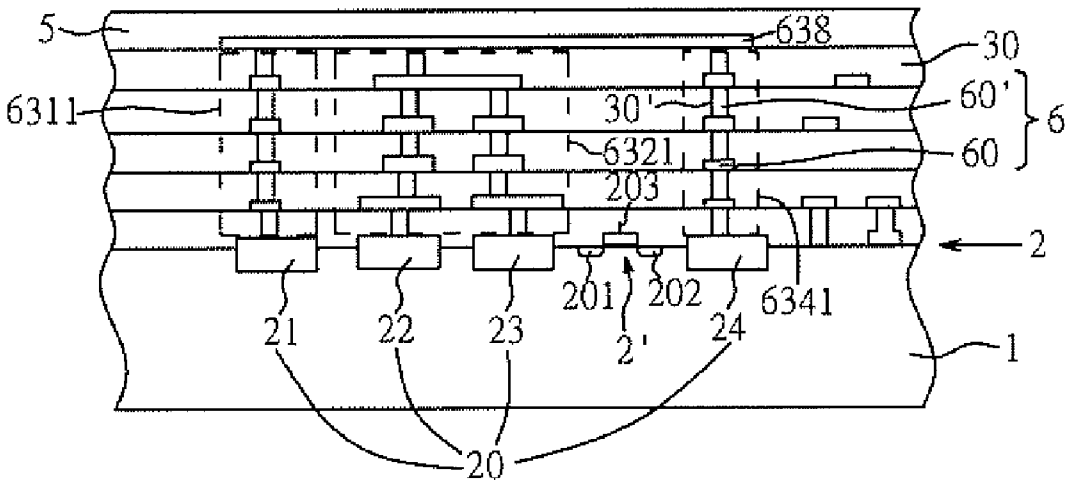
Publication Classification

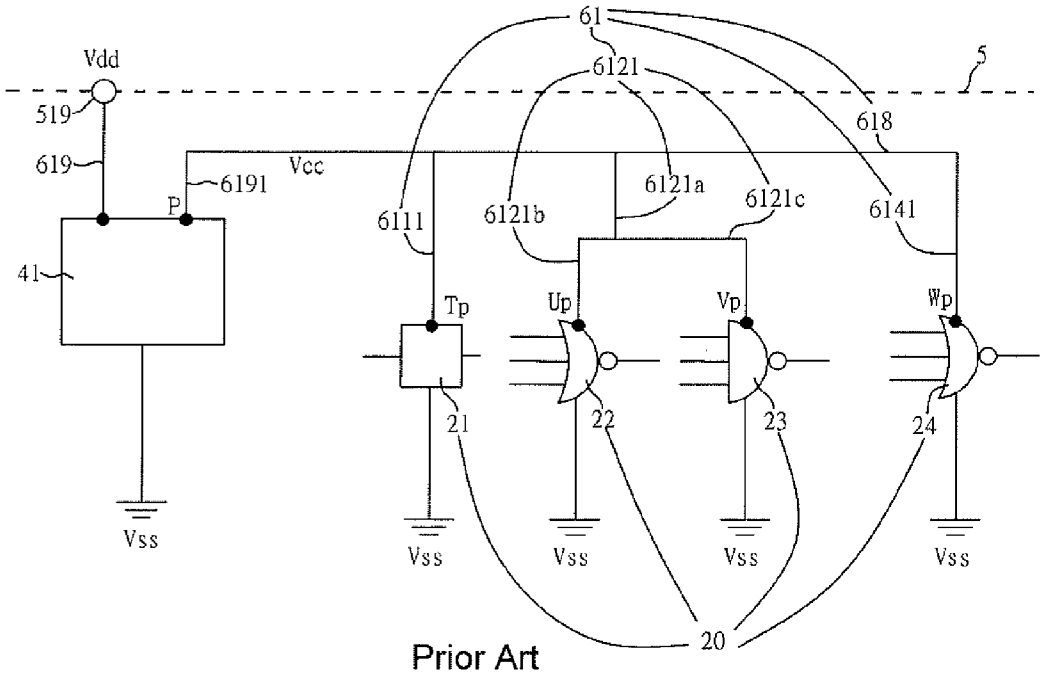
(51) **Int. Cl.**
H05K 7/00 (2006.01)

(52) **U.S. Cl.** **361/783**

(57) **ABSTRACT**

Integrated circuit chips and chip packages are disclosed that include an over-passivation scheme at a top of the integrated circuit chip and a bottom scheme at a bottom of the integrated circuit chip using a top post-passivation technology and a bottom structure technology. The integrated circuit chips can be connected to an external circuit or structure, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the over-passivation scheme or the bottom scheme. Related fabrication techniques are described.





Prior Art

Fig. 1A

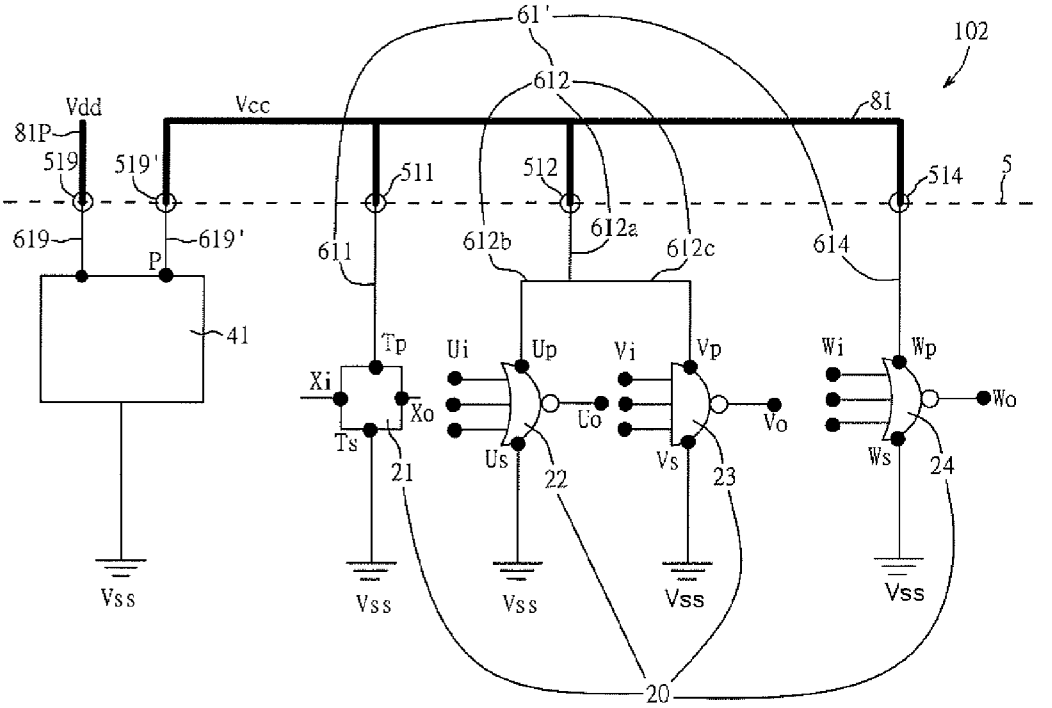


Fig. 1B

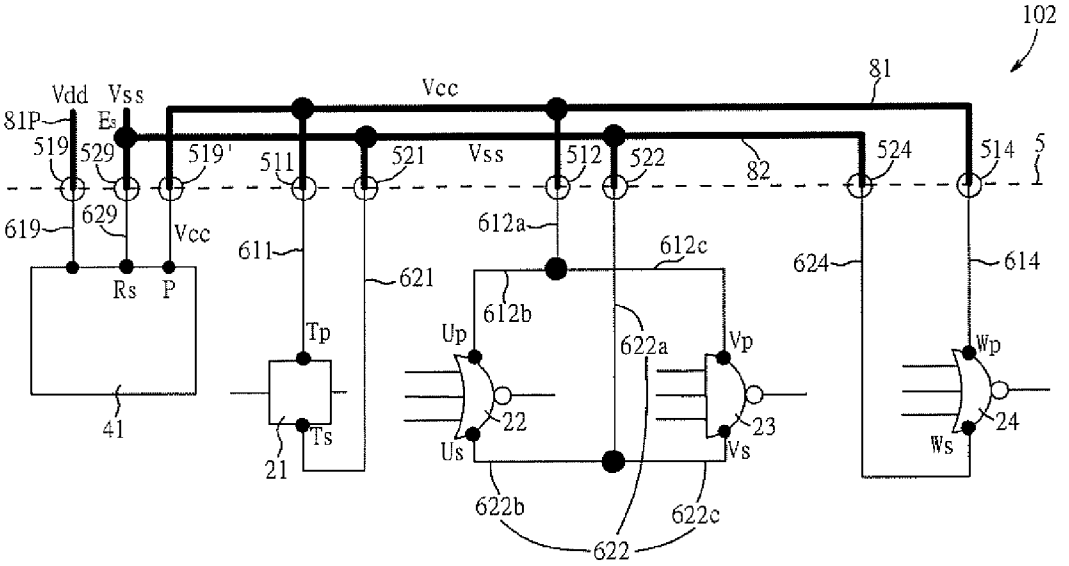

102
81
Vdd
Vss
Vcc
81P
Es
519
529
519'
511
521
Vss
512
522
82
524
514
5
619
629
Vcc
611
621
612a
612c
624
614
Rs
P
612b
Tp
Up
622a
Vp
Wp
41
22
23
24
Ts
Us
Vs
Ws
21
622b
622c
622

Fig. 1C

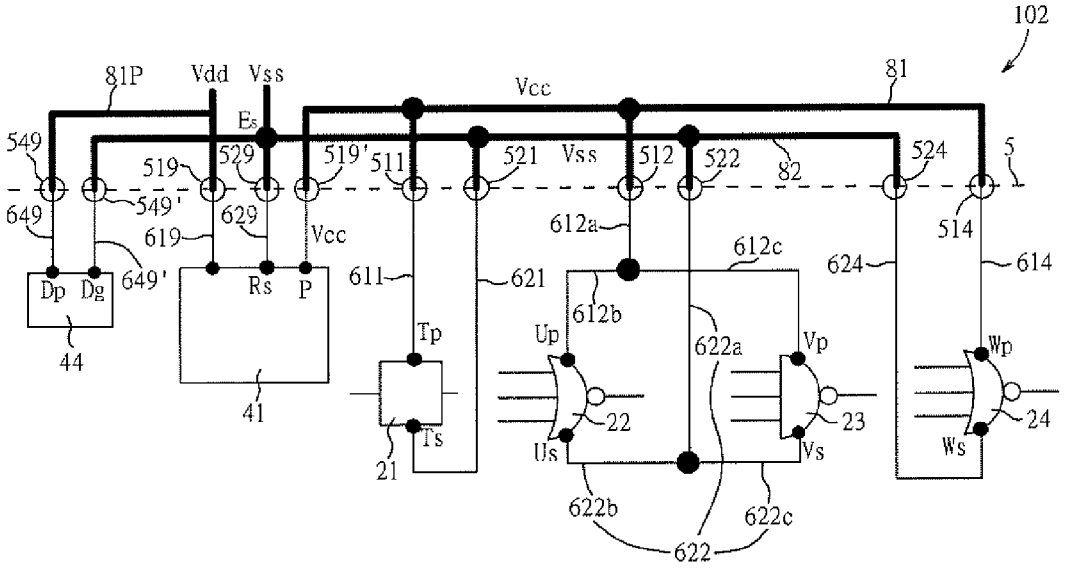

102
81P
Vdd
Vss
81
Vcc
Es
549
519
529
519'
511
521
Vss
512
522
82
524
5
649
549'
629
619
Vcc
612a
612c
514
624
614
Dp
Dg
649'
Rs
P
611
621
612b
622a
Tp
Up
Vp
Wp
44
41
22
23
24
Ts
Us
Vs
Ws
21
622b
622c
622

Fig. 1D

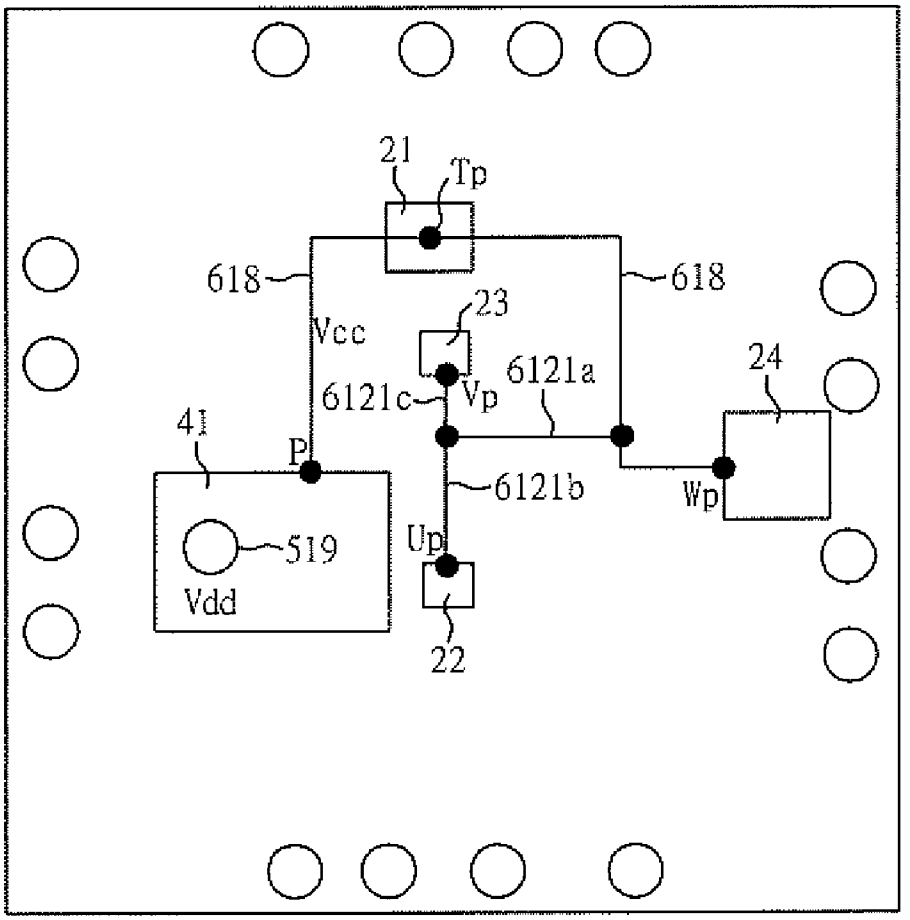


Fig. 2A

Prior Art

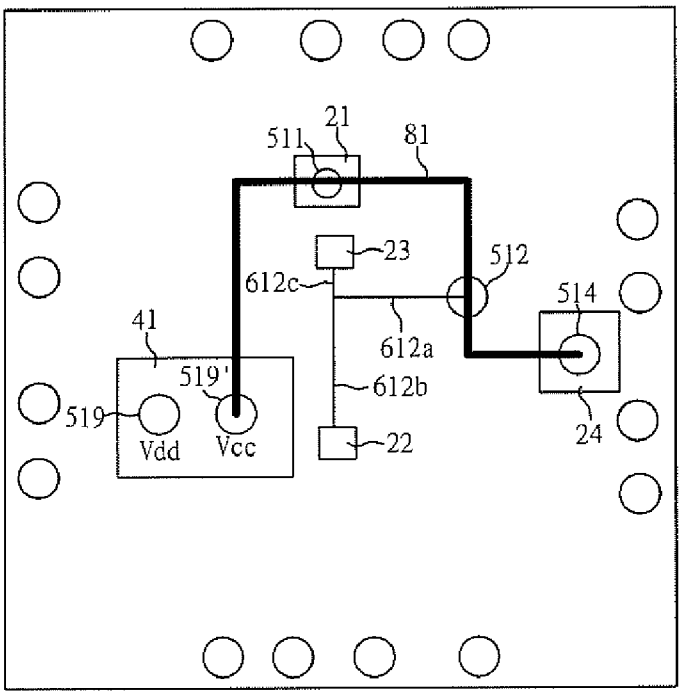

21
511
81
23
512
612c
514
41
612a
519'
612b
519
Vdd
Vcc
22
24

Fig. 2B

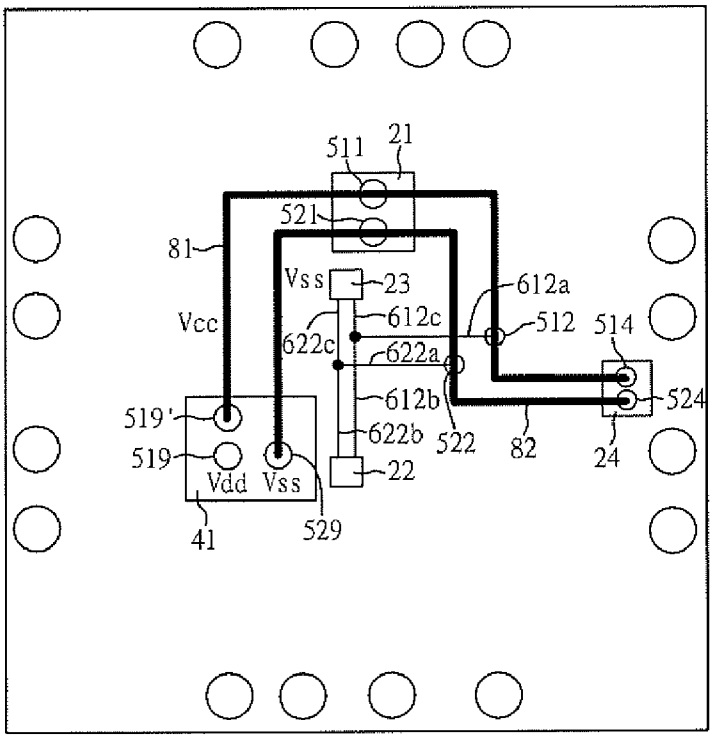

511
21
521
81
Vss
23
612a
Vcc
612c
512
514
622c
622a
612b
524
519'
622b
522
82
519
22
24
Vdd
Vss
41
529

Fig. 2C

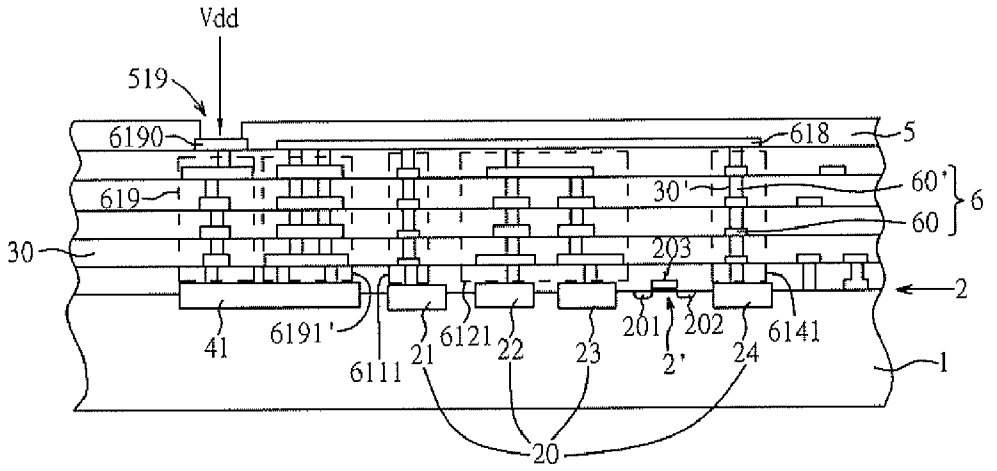


Fig. 3A

Prior Art

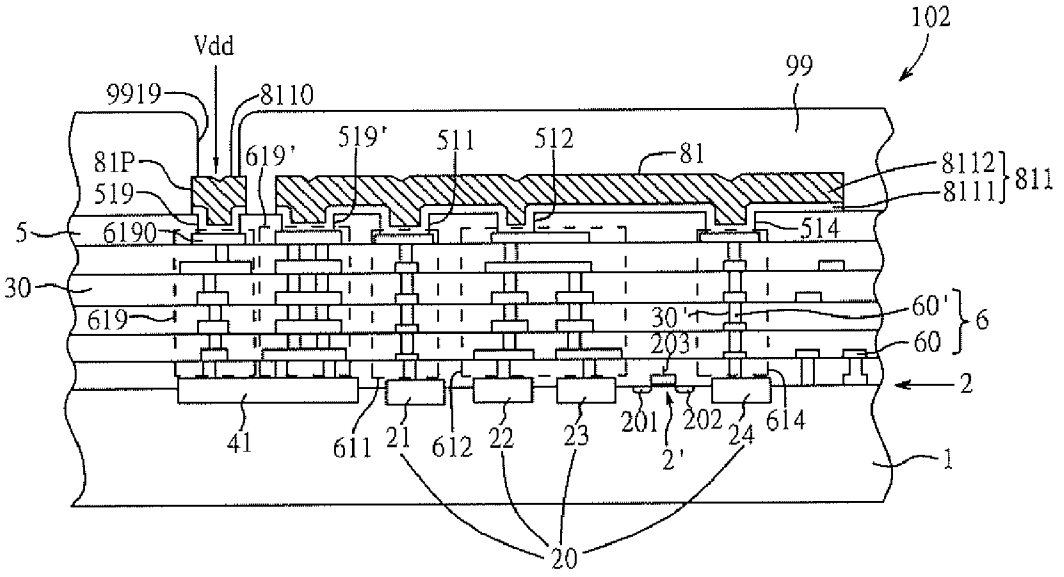


Fig. 3B

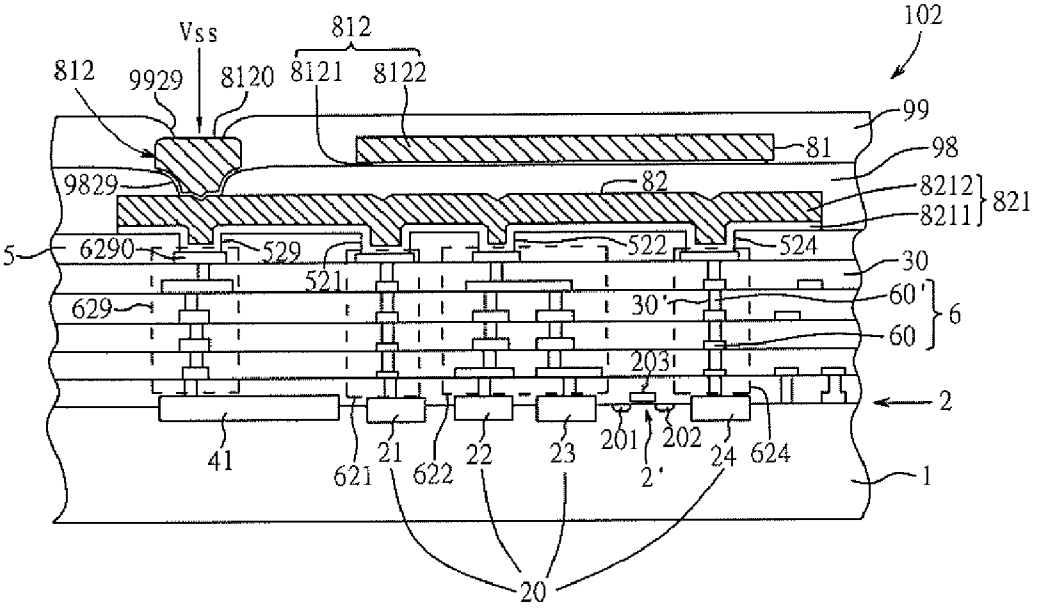

Vss
812
812
9929
8120
8121
8122
102
99
81
98
9829
82
8212
8211
821
5
6290
529
522
524
30
521
629
30'
60'
6
60
203
2
41
621
21
622
22
23
201
202
2'
24
624
1
20

Fig. 3C

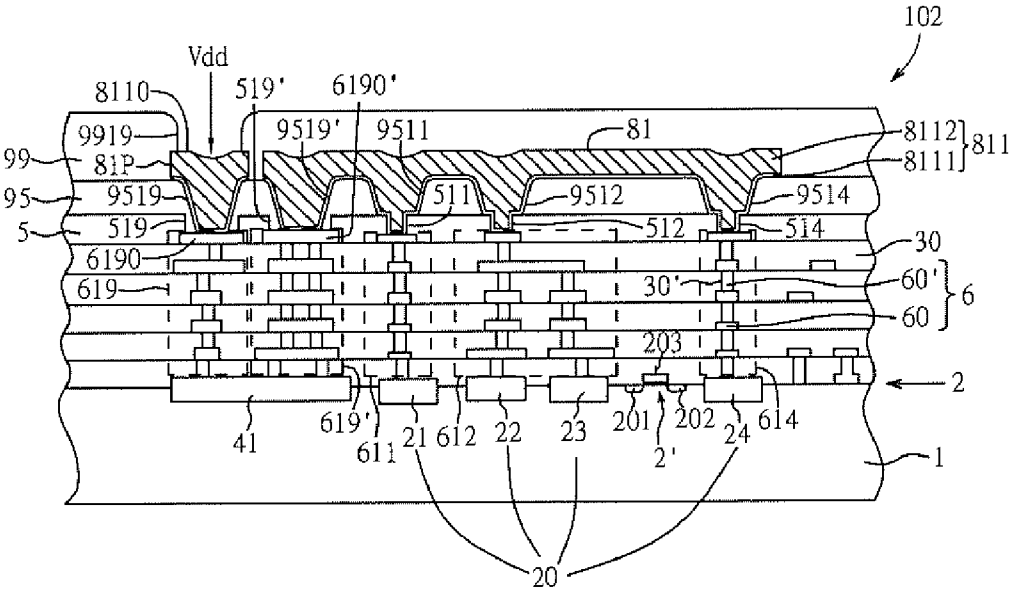

102
Vdd
8110
519'
6190'
9919
9519'
9511
81
8112
8111
811
99
81P
95
9519
511
9512
9514
5
519
512
514
30
6190
619
30'
60'
6
60
203
2
41
619'
611
21
612
22
23
201
202
2'
24
614
1
20

Fig. 3D

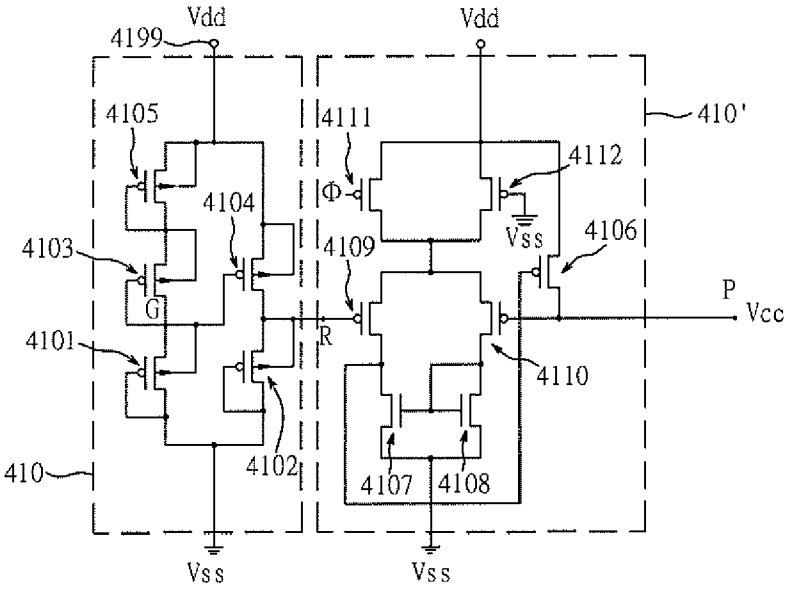

Vdd
4199
Vdd
4105
4111
410'
4112
4104
Φ
Vss
4106
4103
4109
P
Vcc
G
R
4101
4110
410
4102
4107
4108
Vss
Vss

Fig. 4

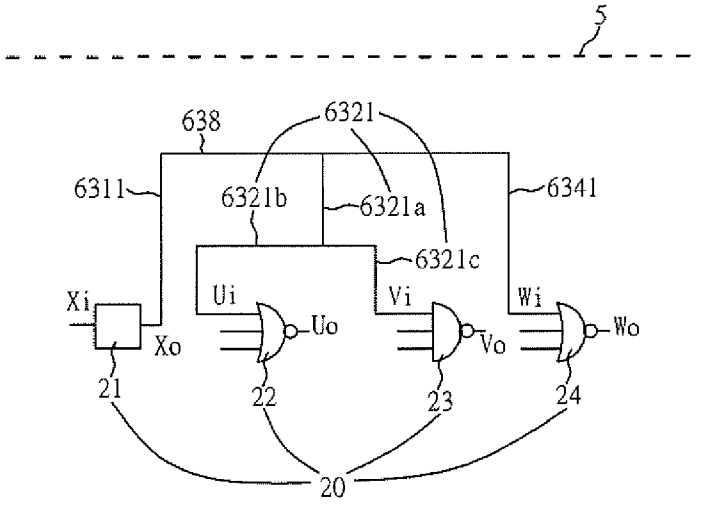

5
638
6321
6311
6321b
6321a
6341
6321c
Xi
Ui
Vi
Wi
Xo
Uo
Vo
Wo
21
22
23
24
20

Fig. 5A

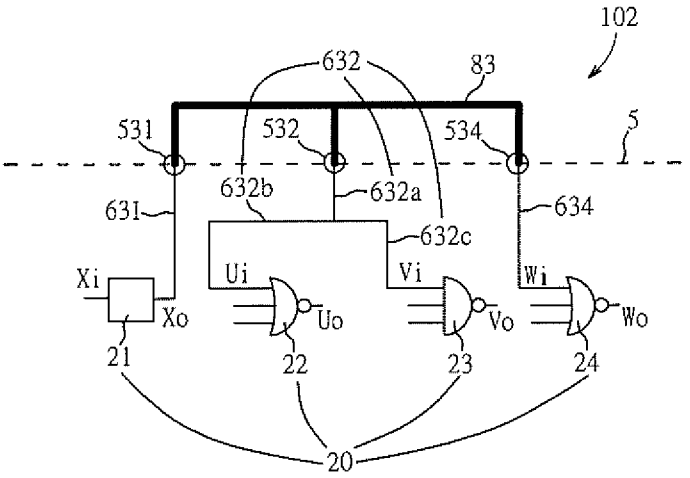

102
632
83
531
532
534
5
632b
632a
631
634
632c
Xi
Ui
Vi
Wi
Xo
Uo
Vo
Wo
21
22
23
24
20

Fig. 5B

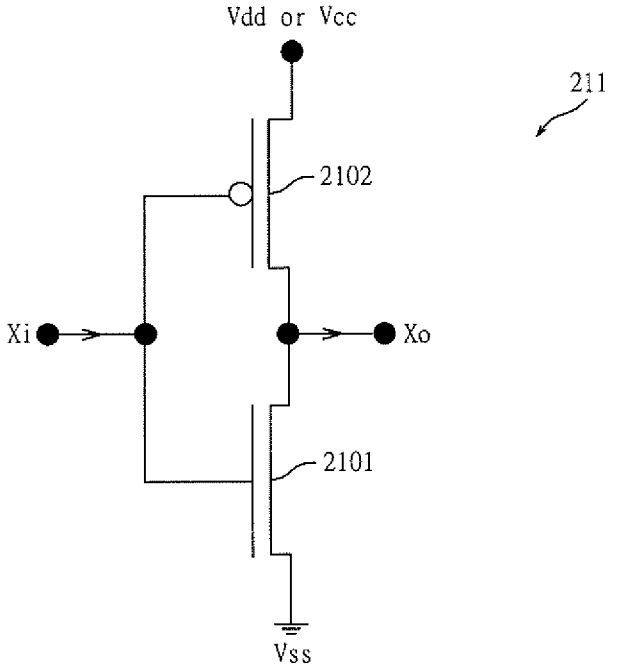

Vdd or Vcc
211
2102
Xi
Xo
2101
Vss

Fig. 5C

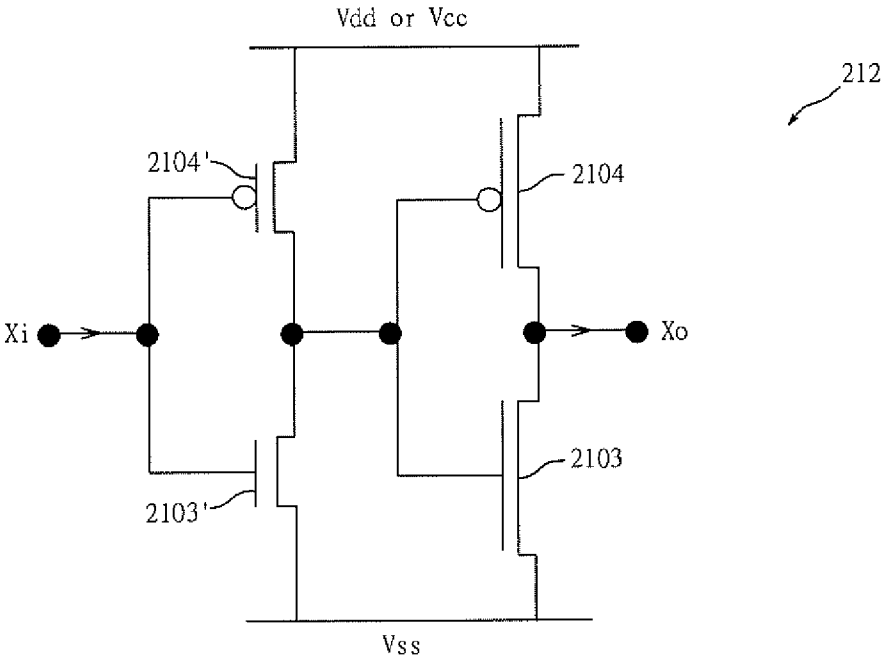

Vdd or Vcc
212
2104'
2104
Xi
Xo
2103
2103'
Vss

Fig. 5D

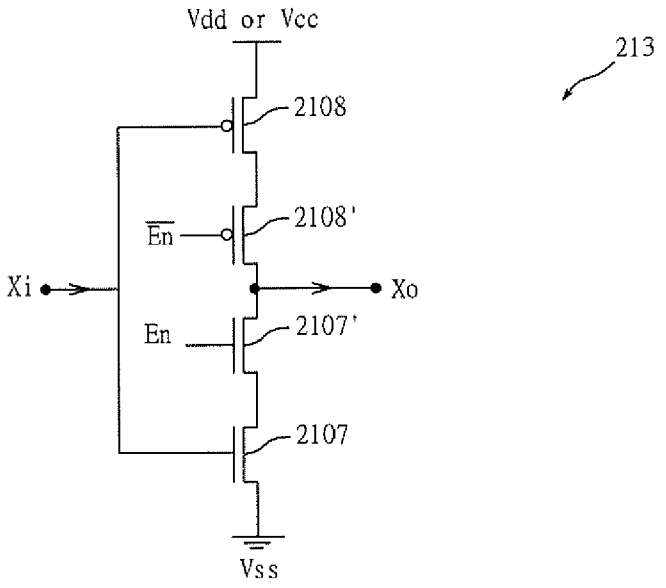

Vdd or Vcc
213
2108
2108'
En
Xi
Xo
En
2107'
2107
Vss

Fig. 5E

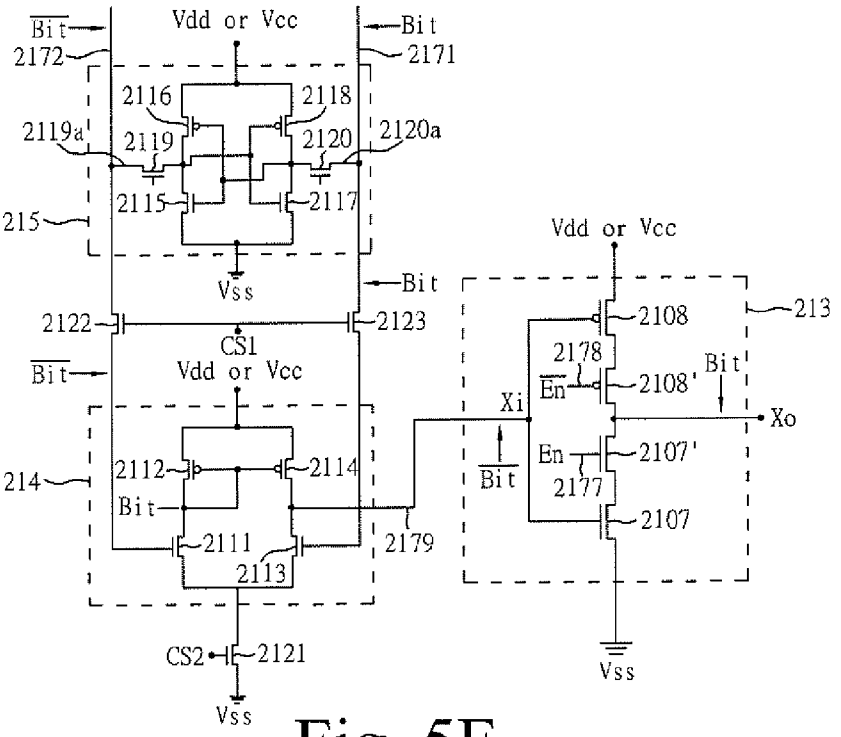

Bit
Vdd or Vcc
Bit
2172
2171
2116
2118
2119a
2119
2120
2120a
2115
2117
215
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
214
2112
2114
Bit
2111
2113
2179
CS2
2121
Vss
Vdd or Vcc
213
2108
2178
En
2108'
Bit
Xi
Xo
En
2107'
Bit
2177
2107
Vss

Fig. 5F

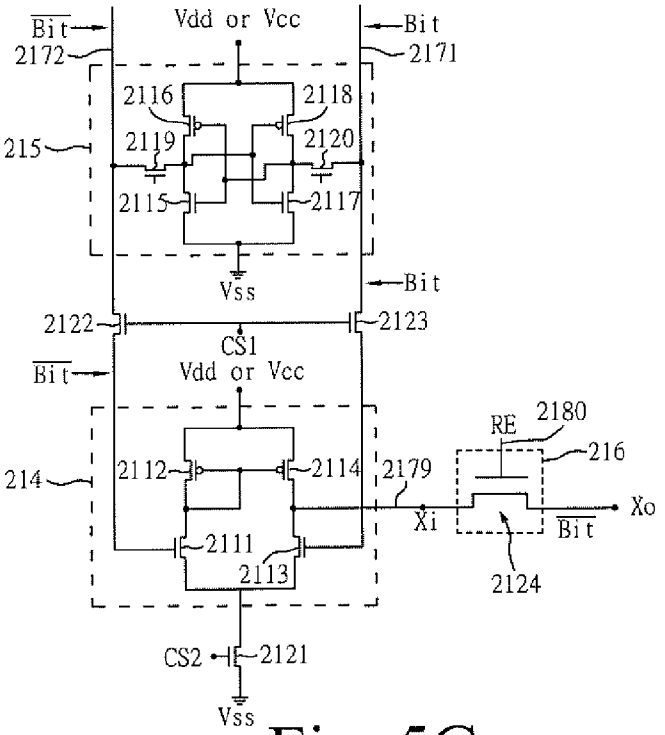

Bit
Vdd or Vcc
Bit
2172
2171
2116
2118
215
2119
2120
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
RE
2180
216
214
2112
2114
2179
Xi
Xo
Bit
2111
2113
2124
CS2
2121
Vss

Fig. 5G

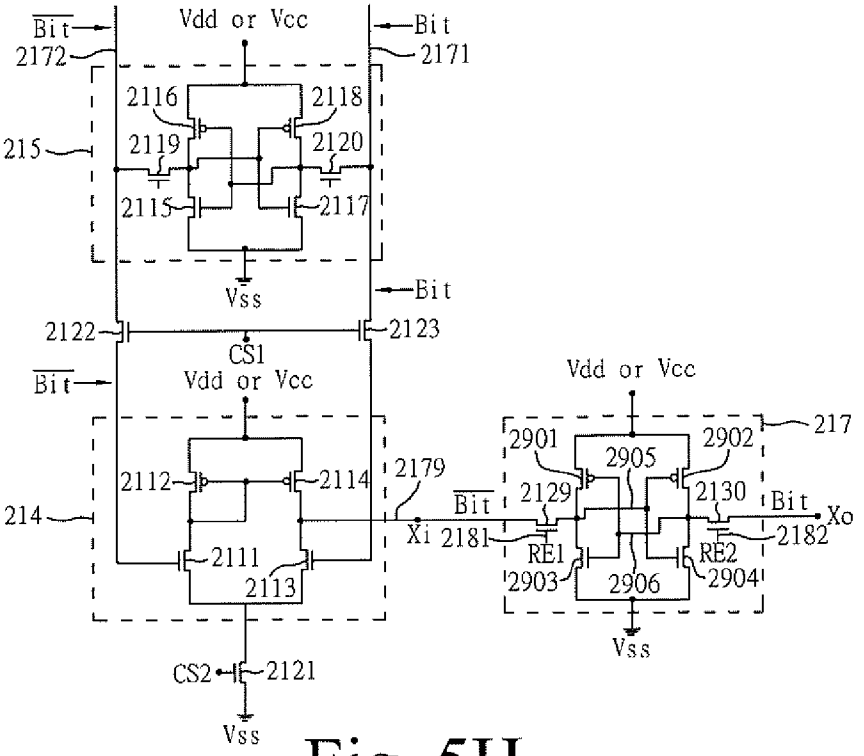

Bit
Vdd or Vcc
Bit
2172
2171
2116
2118
215
2119
2120
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
Vdd or Vcc
217
2901
2905
2902
2112
2114
2179
2129
2130
214
Bit
Bit
Xo
Xi
2181
2182
RE1
RE2
2111
2903
2906
2904
2113
Vss
CS2
2121
Vss

Fig. 5H

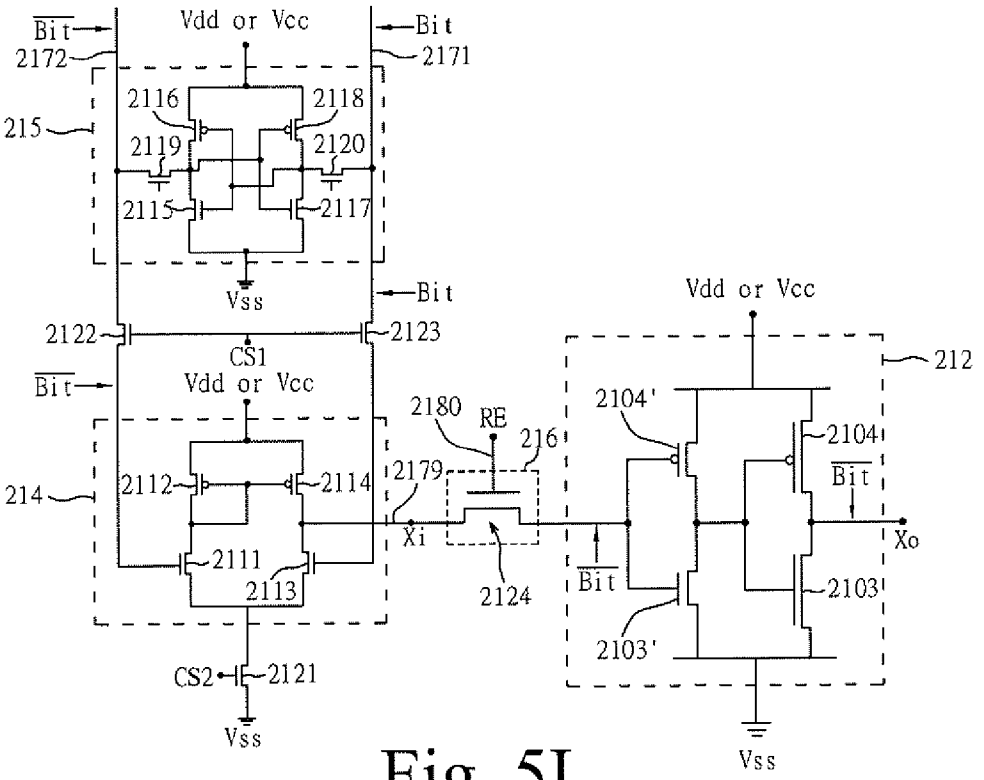

Bit
Vdd or Vcc
Bit
2172
2171
215
2116
2118
2119
2120
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
Vdd or Vcc
212
2180
RE
216
2104'
2104
214
2112
2114
2179
Bit
Xi
Xo
2124
Bit
2103
2111
2113
2103'
CS2
2121
Vss
Vss

Fig. 5I

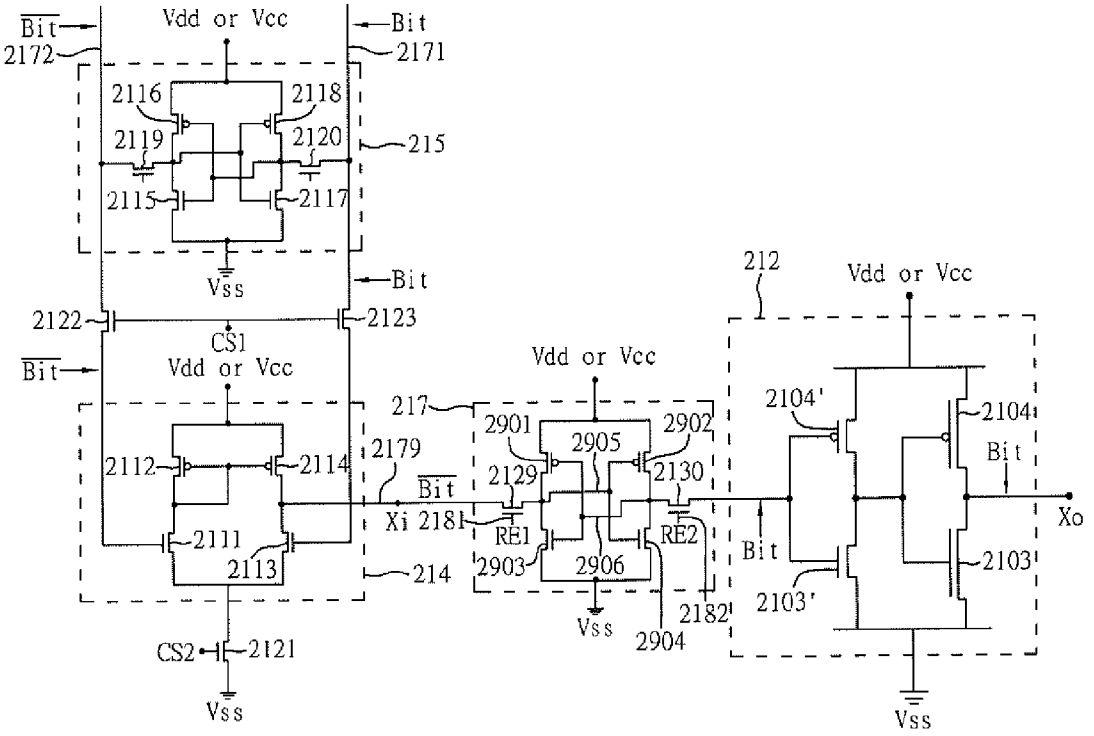

Bit
2172
Vdd or Vcc
Bit
2171
2116
2118
2119
2120
215
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
217
Vdd or Vcc
212
Vdd or Vcc
2104'
2104
Bit
2112
2114
2179
2901
2905
2902
2129
2130
Bit
Xi 218
RE1
RE2
Xo
2111
2113
214
2903
2906
Bit
2103'
2103
2182
Vss
2904
CS2
2121
Vss
Vss

Fig. 5J

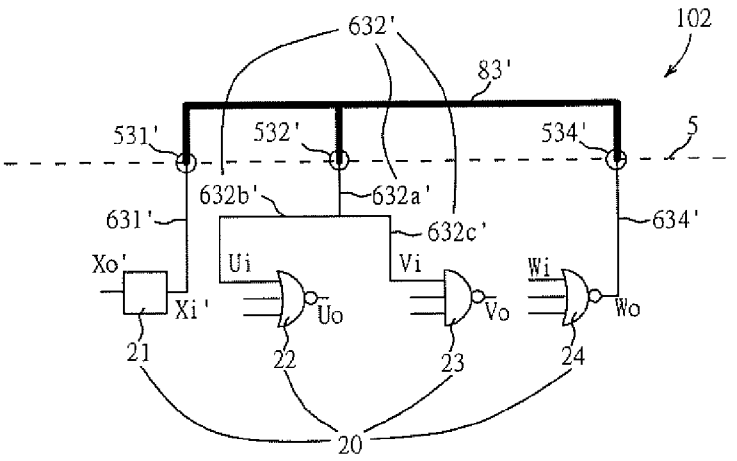

632'
102
83'
531'
532'
534'
5
632b'
632a'
631'
632c'
634'
Xo'
Ui
Vi
Wi
Xi'
Uo
Vo
Wo
21
22
23
24
20

Fig. 5K

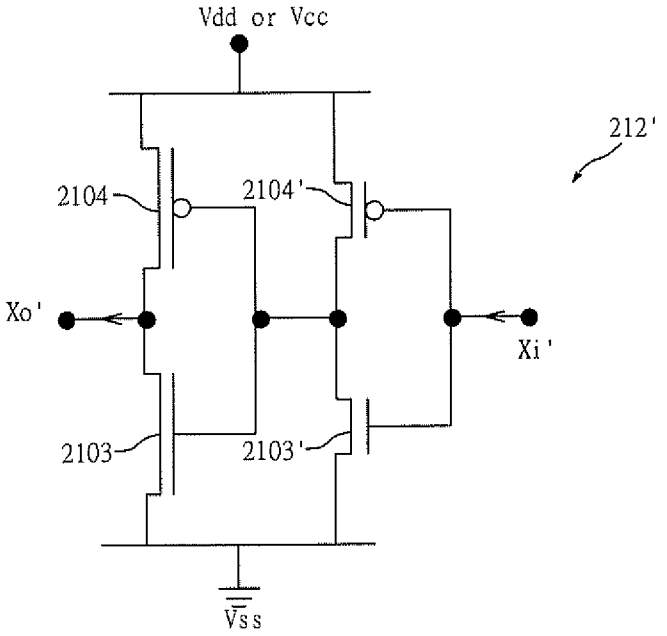

Vdd or Vcc
212'
2104
2104'
Xo'
Xi'
2103
2103'
Vss

Fig. 5L

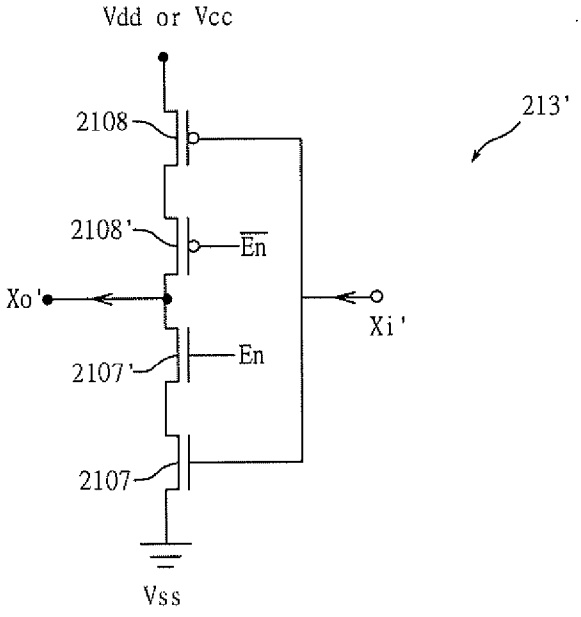

Vdd or Vcc
213'
2108
2108'
En
Xo'
Xi'
2107'
En
2107
Vss

Fig. 5M

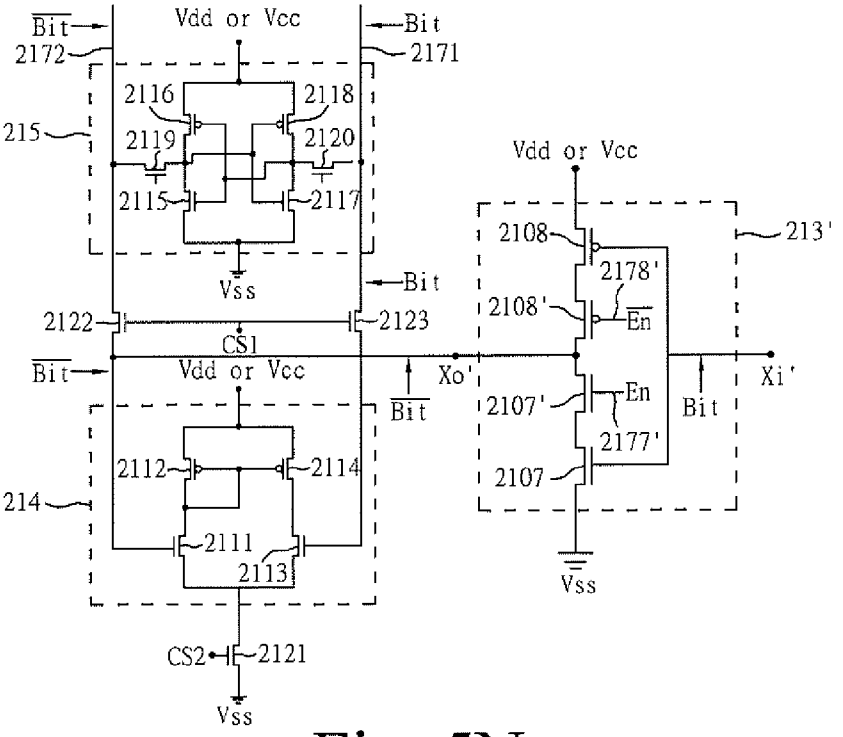

Bit
Vdd or Vcc
Bit
2172
2171
2116
2118
215
2119
2120
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
Xo'
Bit
2112
2114
214
2111
2113
CS2
2121
Vss
Vdd or Vcc
213'
2108
2178'
2108'
En
2107'
En
2177'
2107
Vss
Bit
Xi'

Fig. 5N

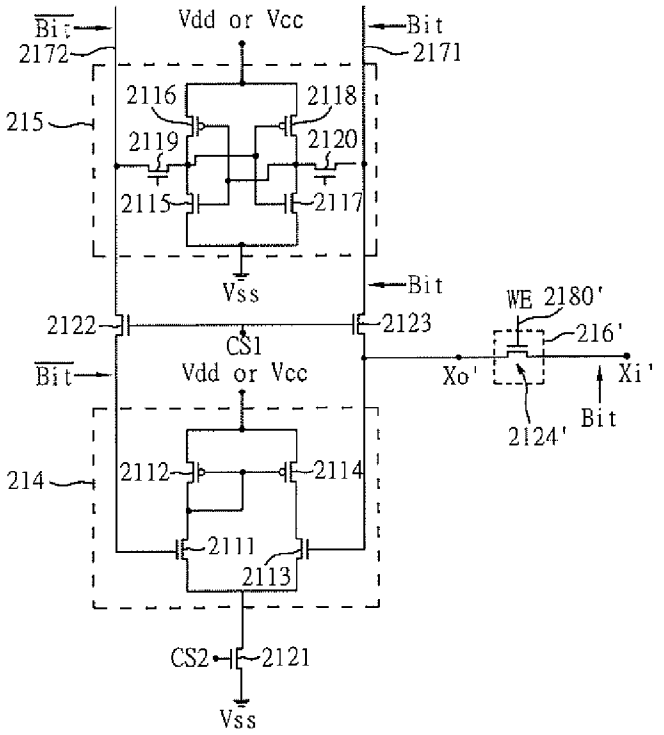

Bit
Vdd or Vcc
Bit
2172
2171
215
2116
2118
2119
2120
2115
2117
Vss
Bit
WE 2180'
2122
2123
216'
CS1
Bit
Vdd or Vcc
Xo'
Xi'
Bit
2124'
214
2112
2114
2111
2113
CS2
2121
Vss

Fig. 5O

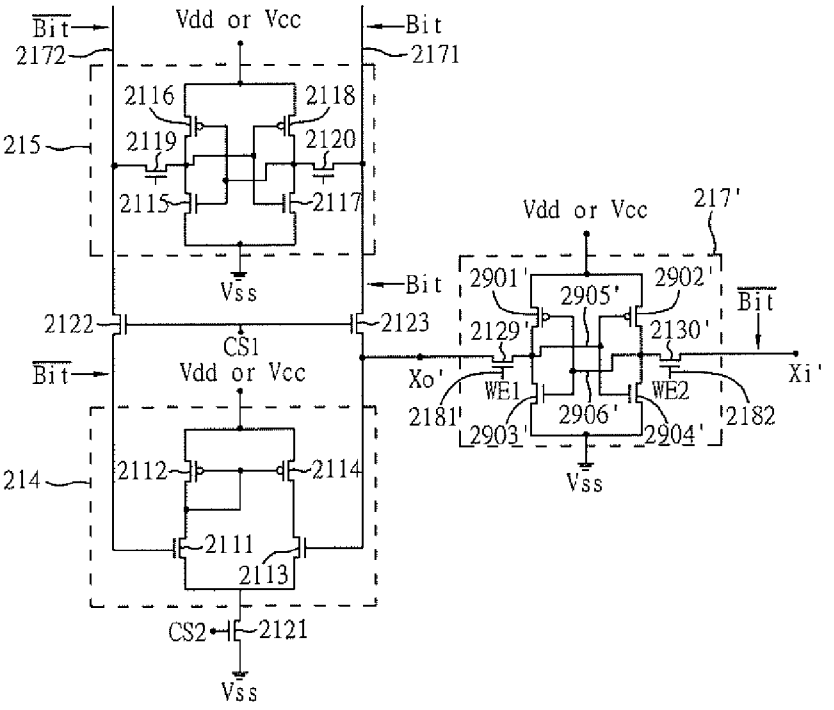

Bit
Vdd or Vcc
Bit
2172
2171
2116
2118
215
2119
2120
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
Xo'
214
2112
2114
2111
2113
CS2
2121
Vss
Vdd or Vcc
217'
2901'
2902'
2905'
Bit
2129'
2130'
WE1
WE2
Xi'
2181'
2903'
2906'
2904'
2182
Vss

Fig. 5P

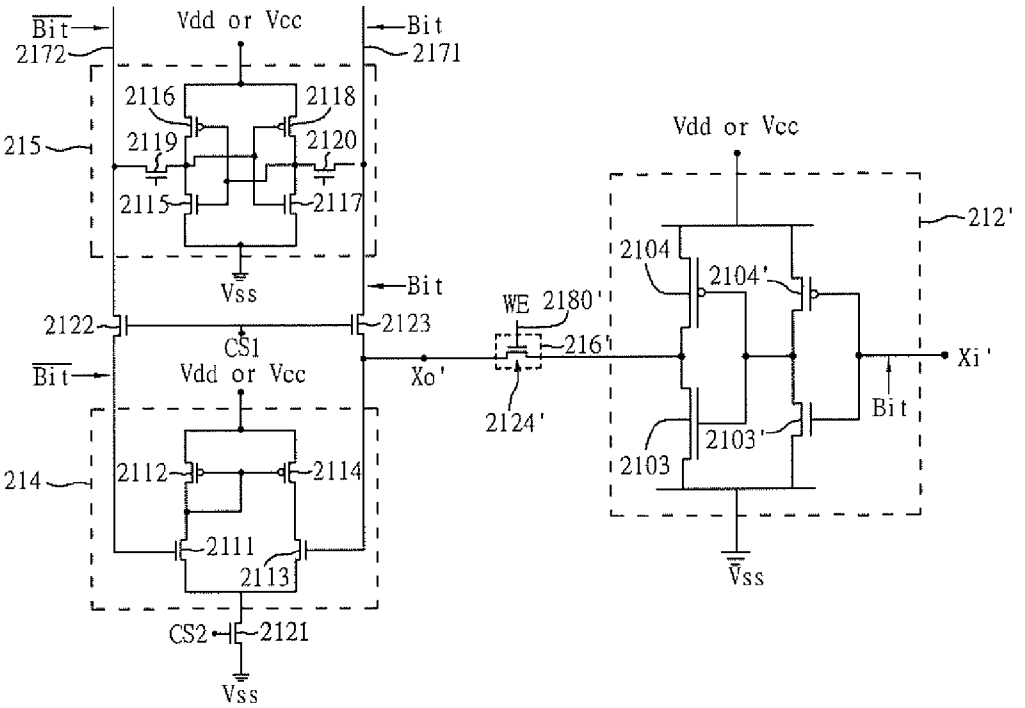

Bit
Vdd or Vcc
Bit
2172
2171
2116
2118
215
2119
2120
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
Xo'
214
2112
2114
2111
2113
CS2
2121
Vss
Vdd or Vcc
212'
2104
2104'
WE 2180'
216'
Xi'
2124'
Bit
2103'
2103
Vss

Fig. 5Q

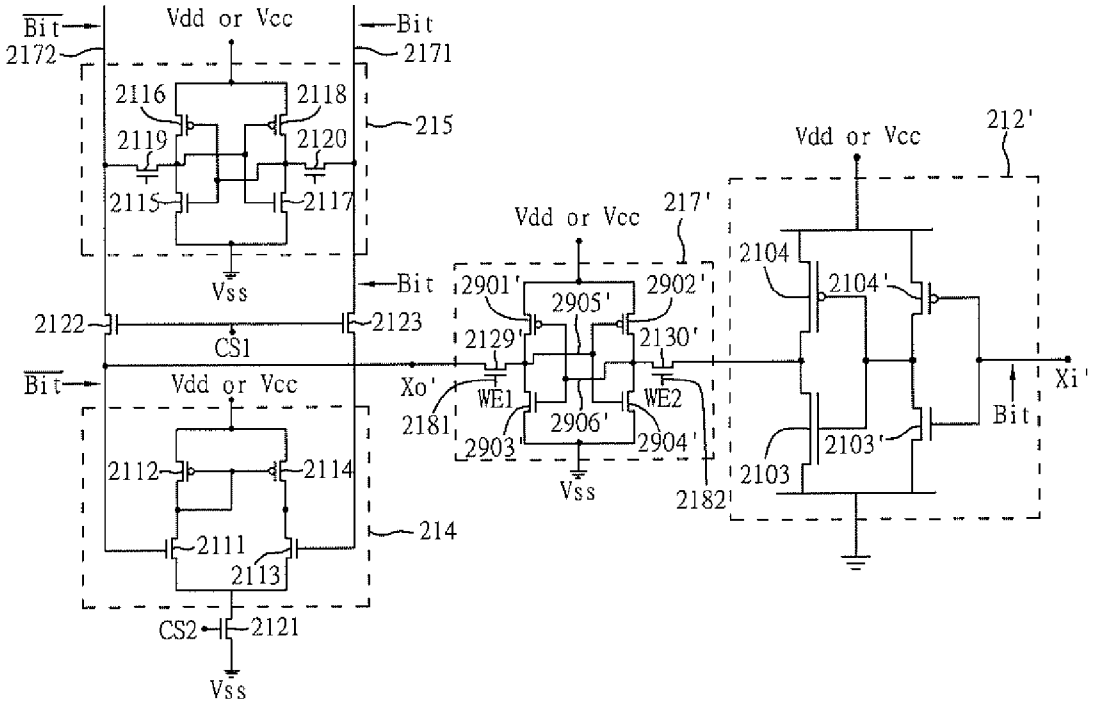

Bit
2172
Vdd or Vcc
Bit
2171
2116
2118
2119
2120
215
2115
2117
Vss
Bit
2122
2123
CS1
Bit
Vdd or Vcc
214
2112
2114
2111
2113
CS2
2121
Vss
Vdd or Vcc
217'
2901'
2902'
2905'
2129'
2130'
Xo'
2181
WE1
WE2
2906'
2903'
2904'
Vss
2182'
Vdd or Vcc
212'
2104
2104'
2103'
2103
Bit
Xi'

Fig. 5R

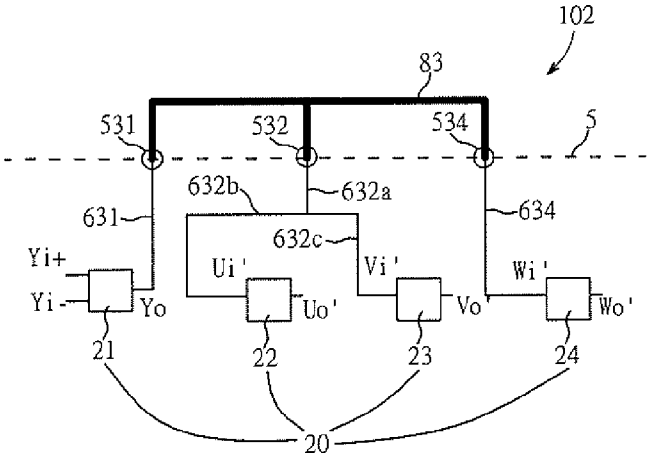

102
83
531
532
534
5
632b
632a
631
634
632c
Yi+
Yi-
Yo
Ui'
Uo'
Vi'
Vo
Wi'
Wo'
21
22
23
24
20

Fig. 5S

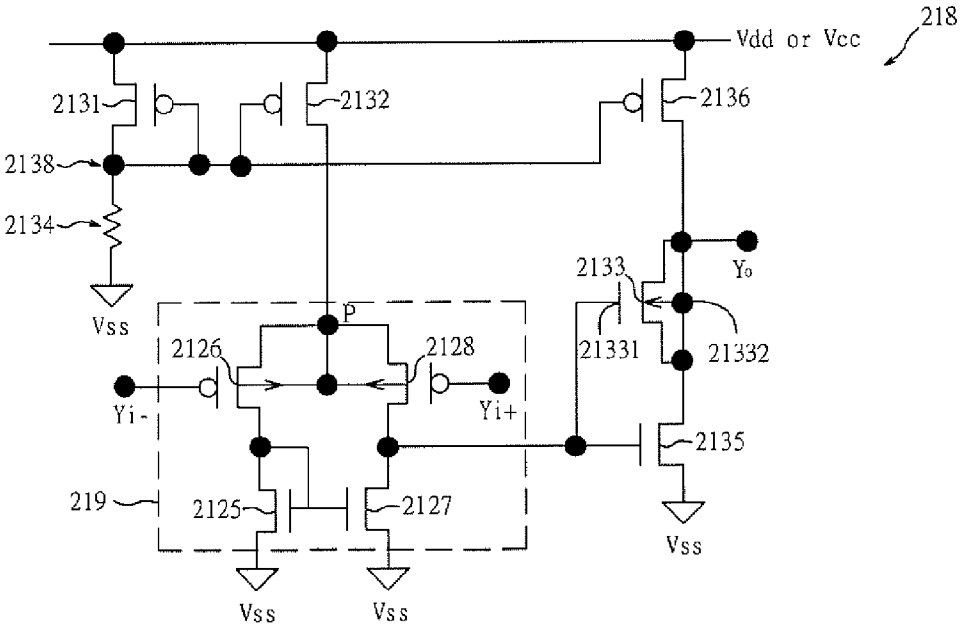

218
Vdd or Vcc
2131
2132
2136
2138
2134
2133
Yo
Vss
P
2126
2128
21331
21332
Yi-
Yi+
2135
219
2125
2127
Vss
Vss
Vss

Fig. 5T

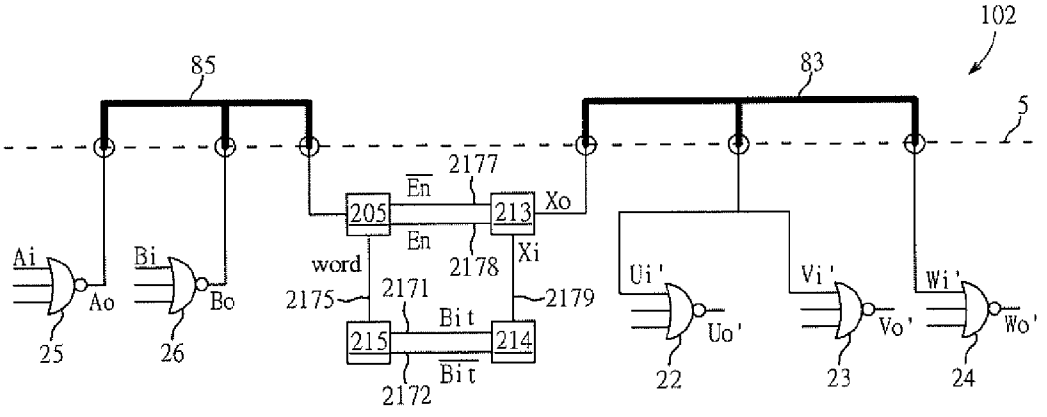

102
85
83
5
2177
En
205
213
Xo
En
2178
Xi
Ai
Bi
word
2175
2171
2179
Bit
215
214
Ao
Bo
Ui'
Vi'
Wi'
Uo'
Vo'
Wo'
25
26
2172
Bit
22
23
24

Fig. 5U

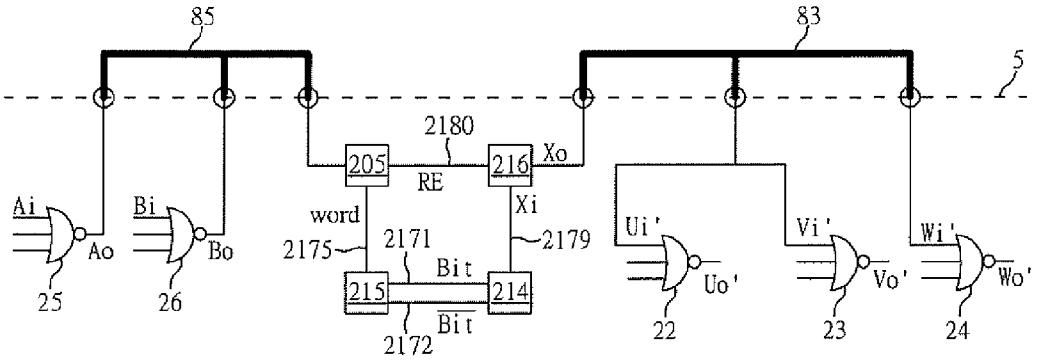

85
83
5
2180
205
216
Xo
RE
Xi
word
2175
2171
2179
Bit
215
214
Bit
2172
Ai
Ao
Bi
Bo
25
26
Ui'
Uo'
Vi'
Vo'
Wi'
Wo'
22
23
24

Fig. 5V

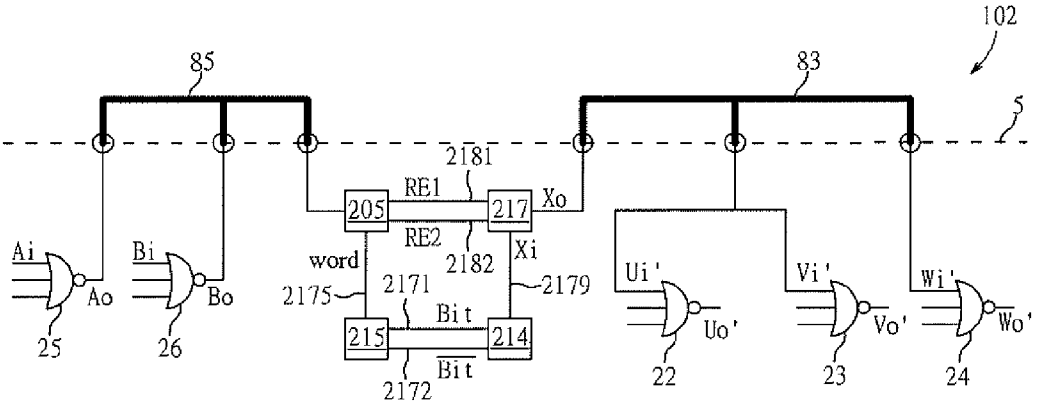

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85
83
5
2181
RE1
205
217
Xo
RE2
2182
Xi
word
2175
2171
2179
Bit
215
214
Bit
2172
Ai
Ao
Bi
Bo
25
26
Ui'
Uo'
Vi'
Vo'
Wi'
Wo'
22
23
24

Fig. 5W

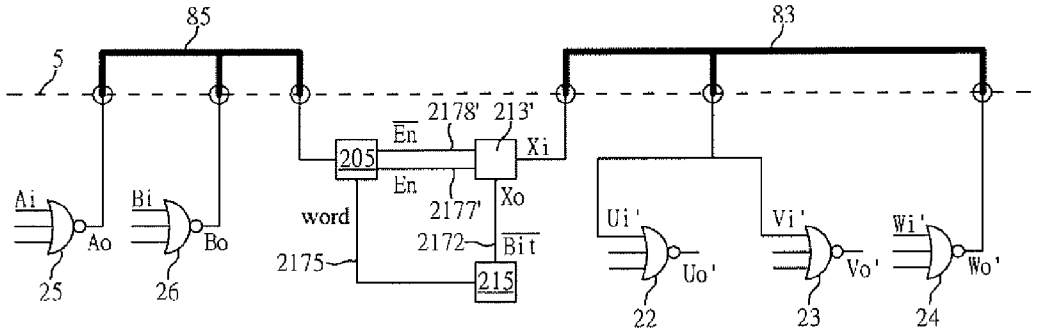

85
83
5
2178'
213'
En
Xi
205
En
2177'
Xo
word
2172
Bit
2175
215
Ai
Bi
Ao
Bo
25
26
Ui'
Vi'
Wi'
Uo'
Vo'
Wo'
22
23
24

Fig. 5X

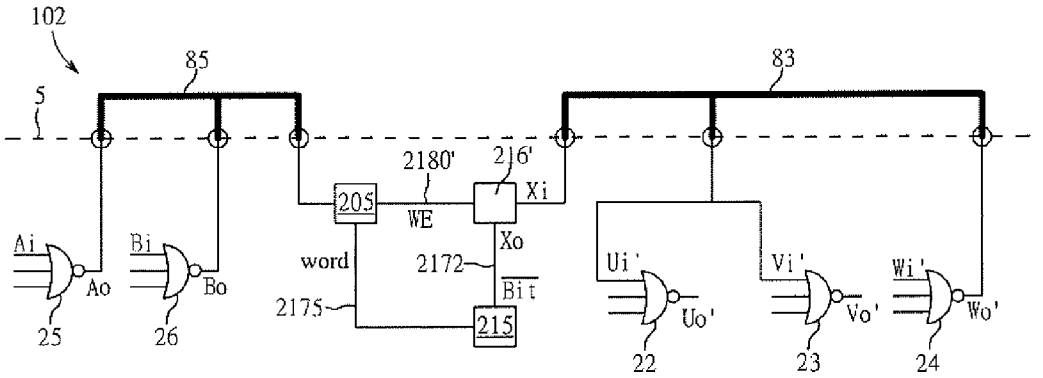

102
85
83
5
2180'
216'
Xi
205
WE
Xo
word
2172
Bit
2175
215
Ai
Bi
Ao
Bo
25
26
Ui'
Vi'
Wi'
Uo'
Vo'
Wo'
22
23
24

Fig. 5Y

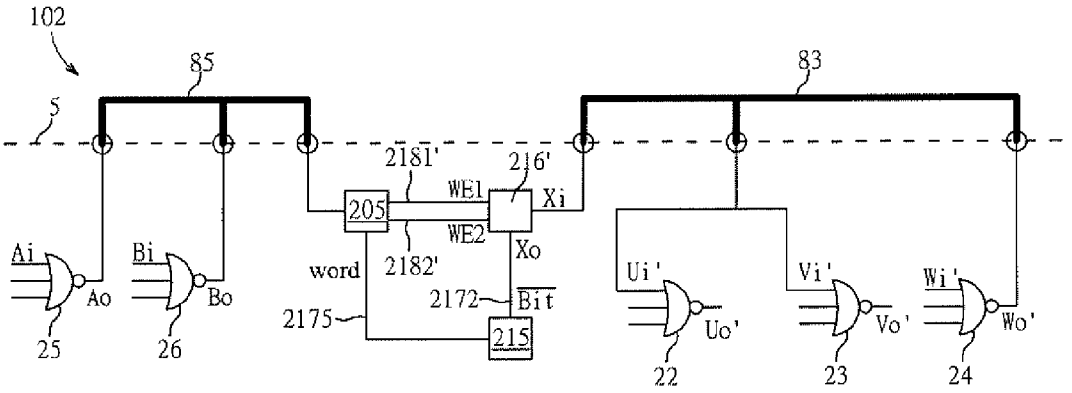

102
85
83
5
2181'
216'
WE1
Xi
205
WE2
Xo
Ai
Bi
word
2182'
Ui'
Vi'
Wi'
Ao
Bo
2172
Bit
2175
215
Uo'
Vo'
Wo'
25
26
22
23
24

Fig. 5Z

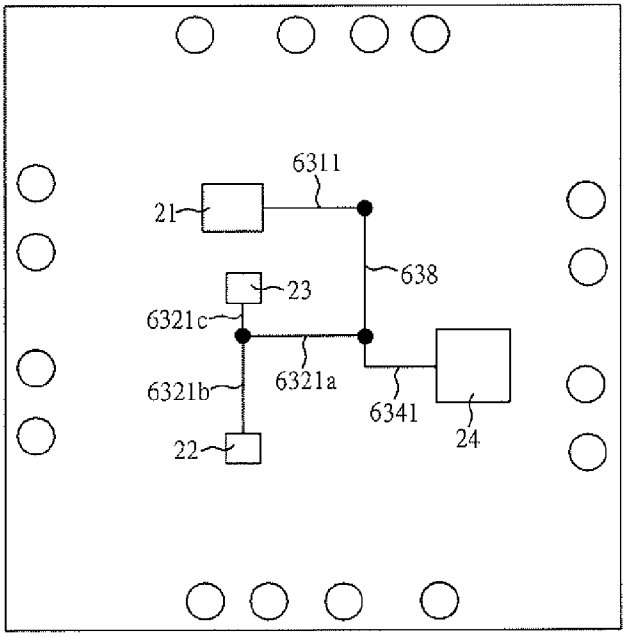

6311
21
638
23
6321c
6321a
6321b
6341
24
22

Fig. 6A

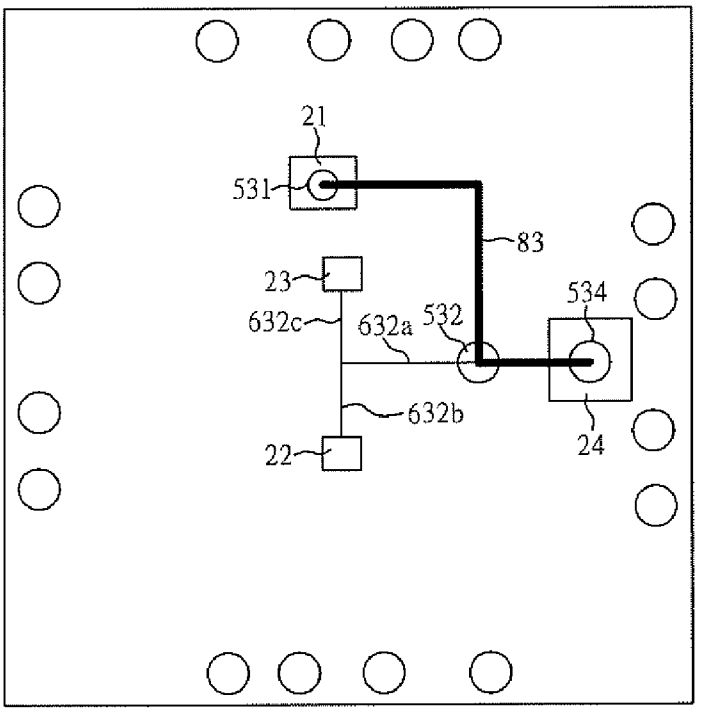

21
531
83
23
534
632c
632a
532
632b
22
24

Fig. 6B

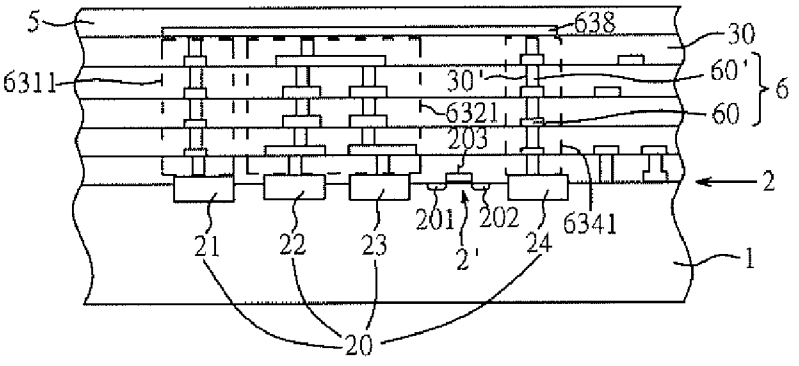

5
638
30
6311
60'
6
30'
6321
60
203
2
201
202
6341
21
22
23
2'
24
1
20

Fig. 7A

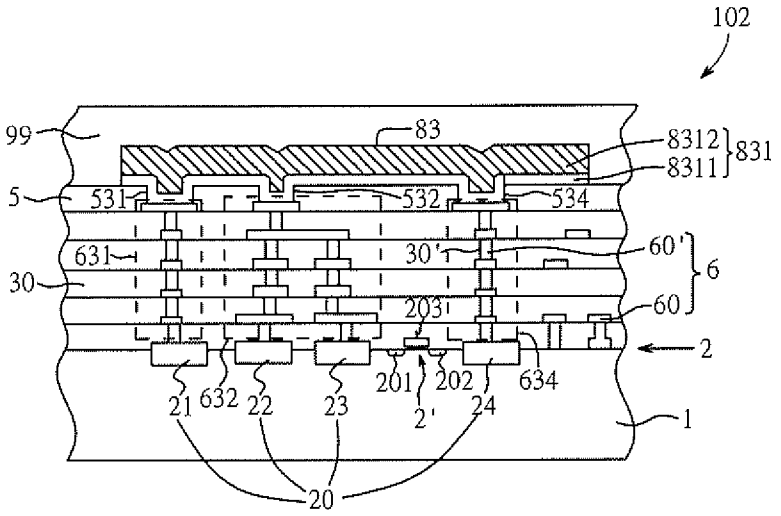

102
99
83
8312
8311
831
5
531
532
534
631
30'
60'
6
30
203
60
2
21
632
22
23
201
202
2'
24
634
1
20

Fig. 7B

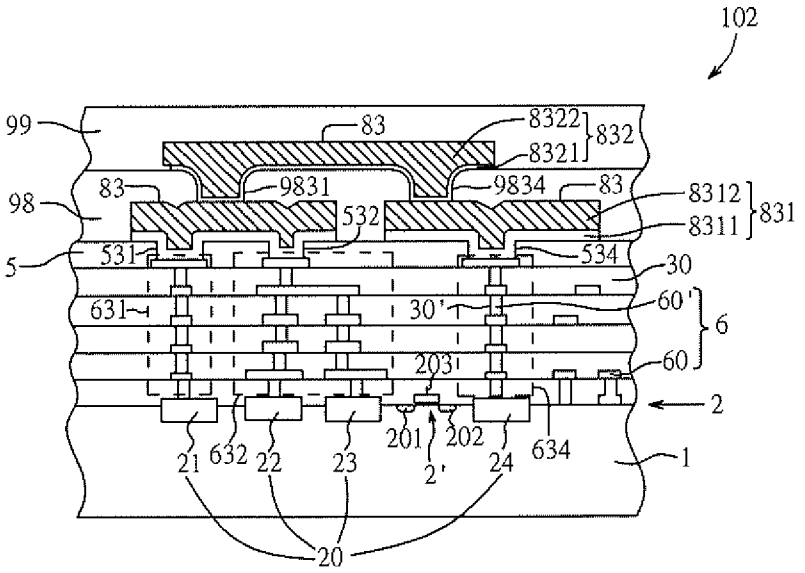

102
99
83
8322
8321
832
98
9831
9834
8312
8311
831
532
5
531
534
30
631
30'
60'
6
203
60
2
21
632
22
23
201
202
2'
24
634
1
20

Fig. 7C

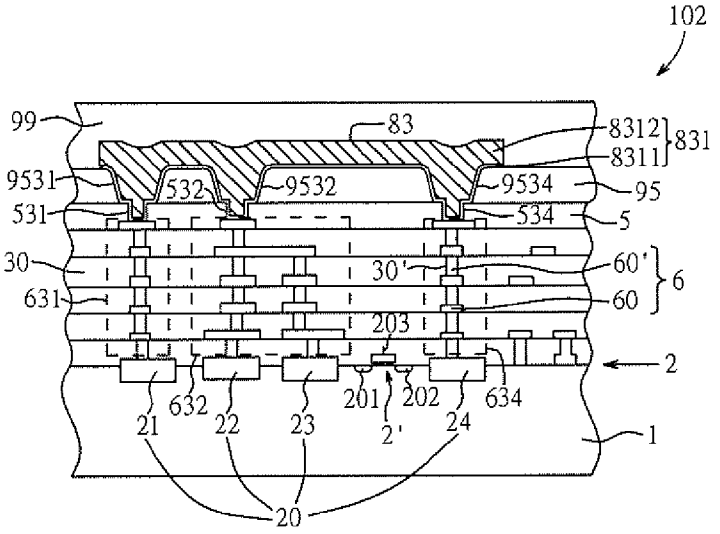

102
99
83
8312
8311
831
9531
532
9532
9534
95
531
534
5
30
30'
60'
6
631
60
203
2
632
201
202
634
21
22
23
2'
24
1
20

Fig. 7D

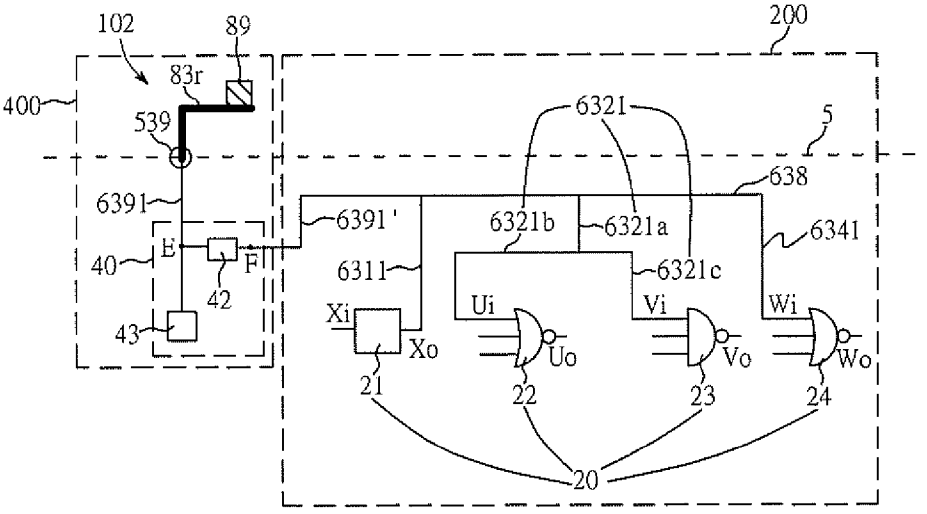

102
89
200
400
83r
539
6321
5
638
6391
6391'
6321b
6321a
6341
40
E
F
6311
6321c
42
Xi
Ui
Vi
Wi
43
Xo
Uo
Vo
Wo
21
22
23
24
20

Fig. 8A

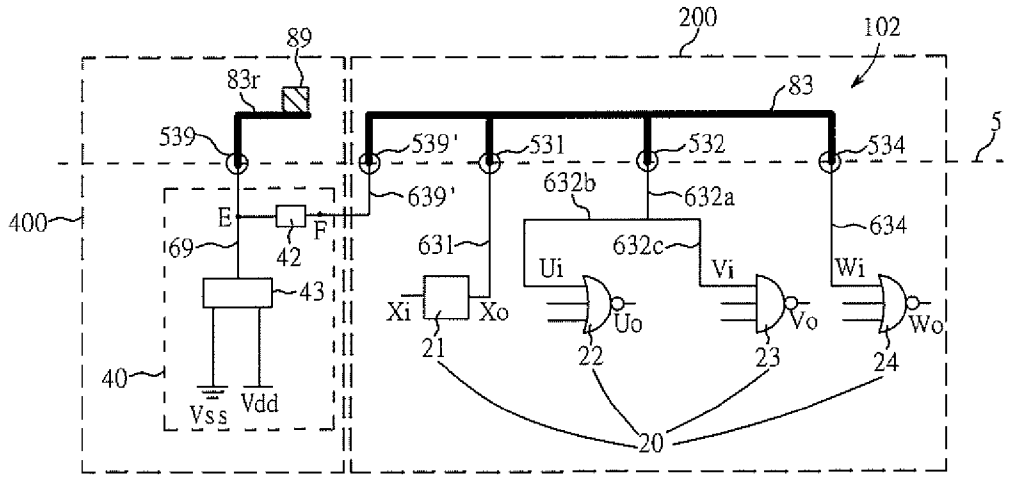

200
102
89
83r
83
539
539'
531
532
534
5
400
639'
632b
632a
E
F
69
42
631
632c
634
Ui
Vi
Wi
43
Xi
Xo
Uo
Vo
Wo
21
22
23
24
40
Vss
Vdd
20

Fig. 8B

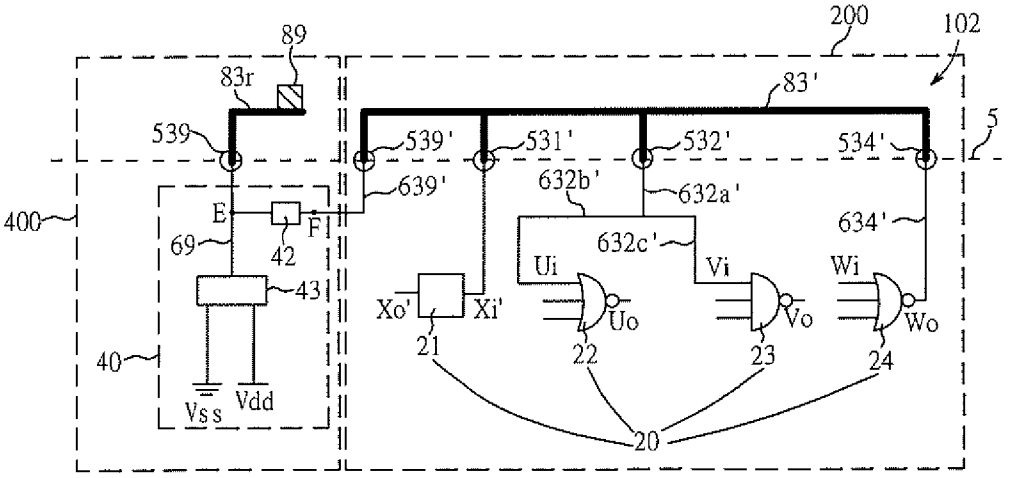

200
102
89
83r
83'
539
539'
531'
532'
534'
5
400
639'
632b'
632a'
E
F
69
42
634'
632c'
Ui
Vi
Wi
43
Xo'
Xi'
Uo
Vo
Wo
21
22
23
24
40
Vss
Vdd
20

Fig. 8C

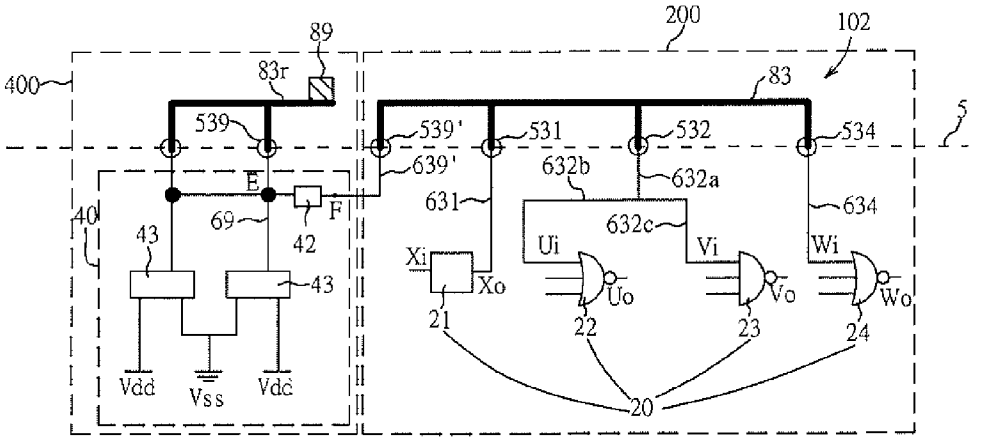

400
89
83r
539
E
F
69
42
43
40
Vdd
Vss
Vdd
200
102
83
539'
531
532
534
5
639'
631
632b
632a
632c
634
Ui
Vi
Wi
Xi
Xo
Uo
Vo
Wo
21
22
23
24
20

Fig. 8D

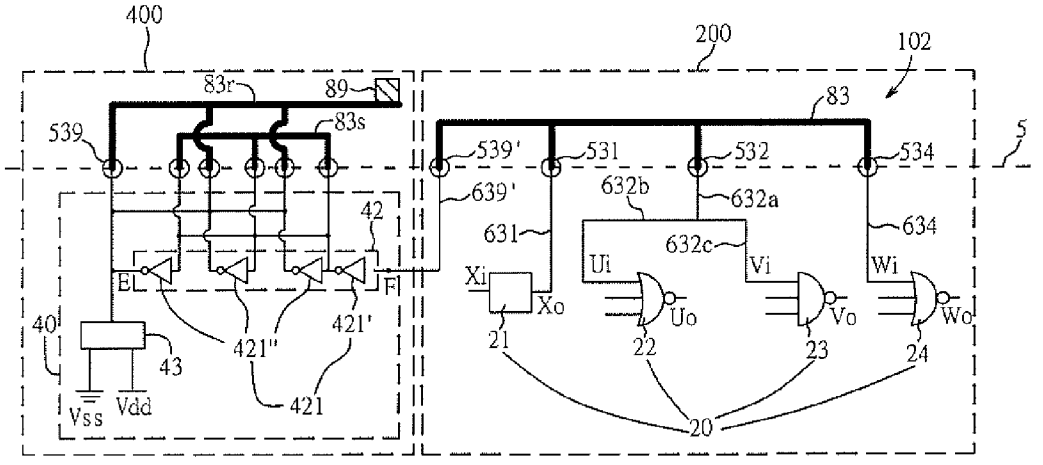

400
83r
89
83s
539
42
EL
F
40
43
421''
421'
421
Vss
Vdd
200
102
83
539'
531
532
534
5
639'
631
632b
632a
632c
634
Ui
Vi
Wi
Xi
Xo
Uo
Vo
Wo
21
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23
24
20

Fig. 8E

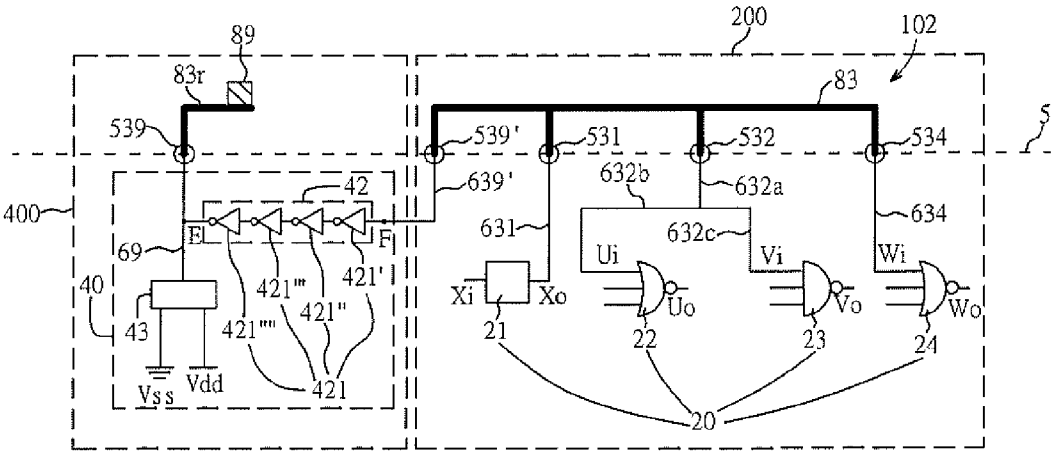

89
83r
539
200
102
83
539'
531
532
534
5
400
42
639'
632b
632a
634
631
632c
69
Fl
Fl
Ui
Vi
Wi
421'''
421'
40
421''
Xi
Xo
Uo
Vo
Wo
43
421''''
421''
21
22
23
24
Vss
Vdd
421
20

Fig. 8F

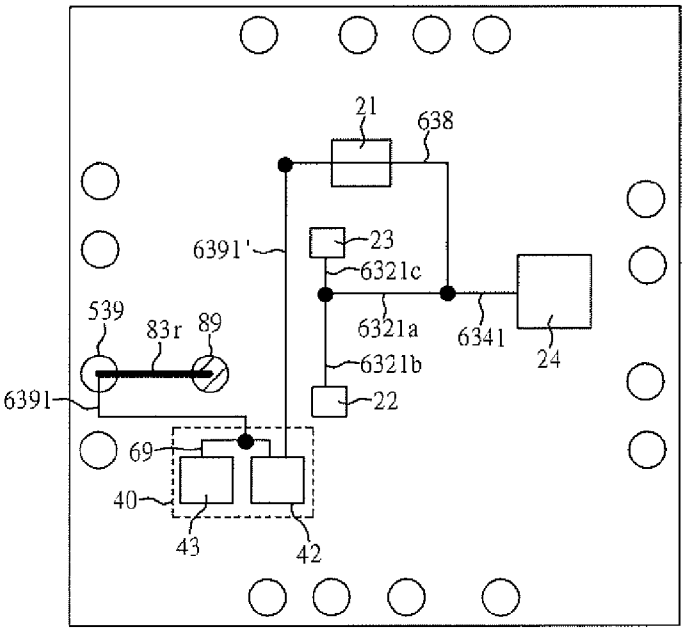

21
638
6391'
23
6321c
539
83r
89
6321a
6341
24
6321b
6391
22
69
40
43
42

Fig. 9A

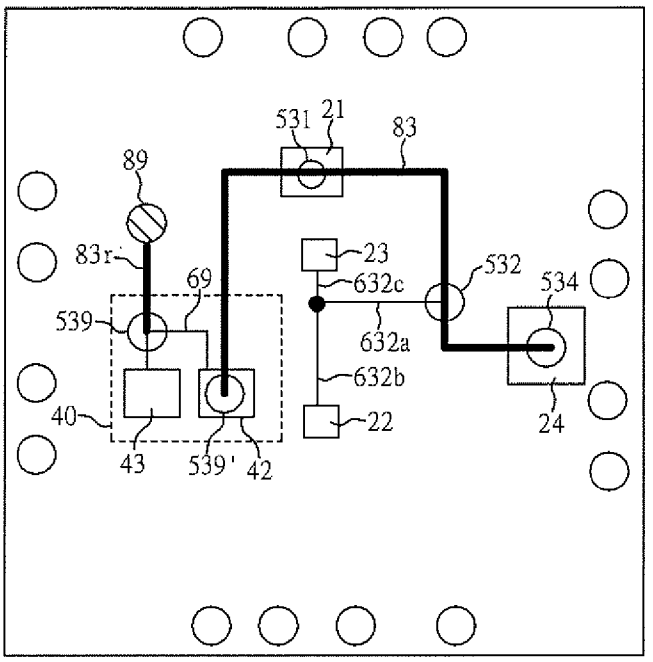

531
21
83
89
83r
69
23
632c
532
534
539
632a
632b
40
22
24
43
539'
42

Fig. 9B

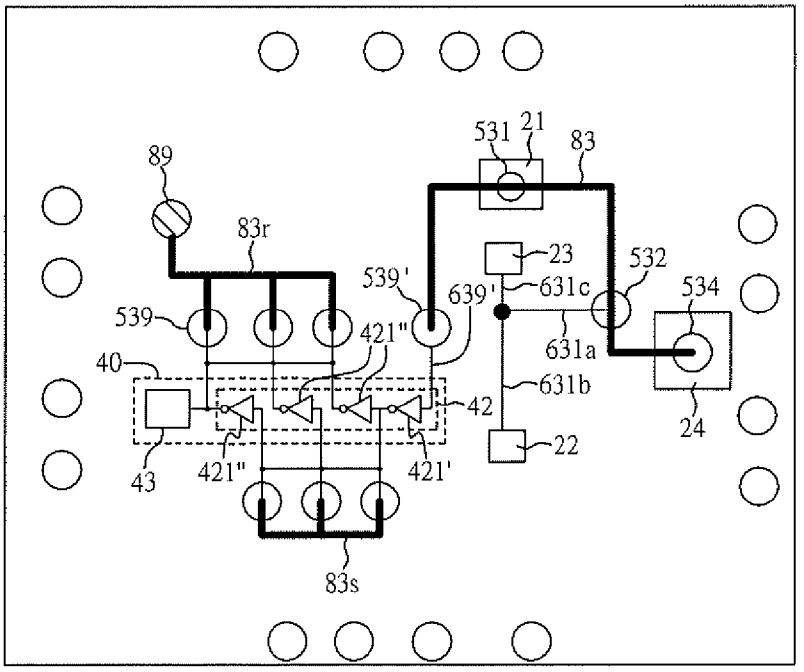

531
21
83
89
83r
23
532
539'
631c
534
539
639'
421"
631a
40
631b
42
22
24
43
421"
421'
83s

Fig. 9C

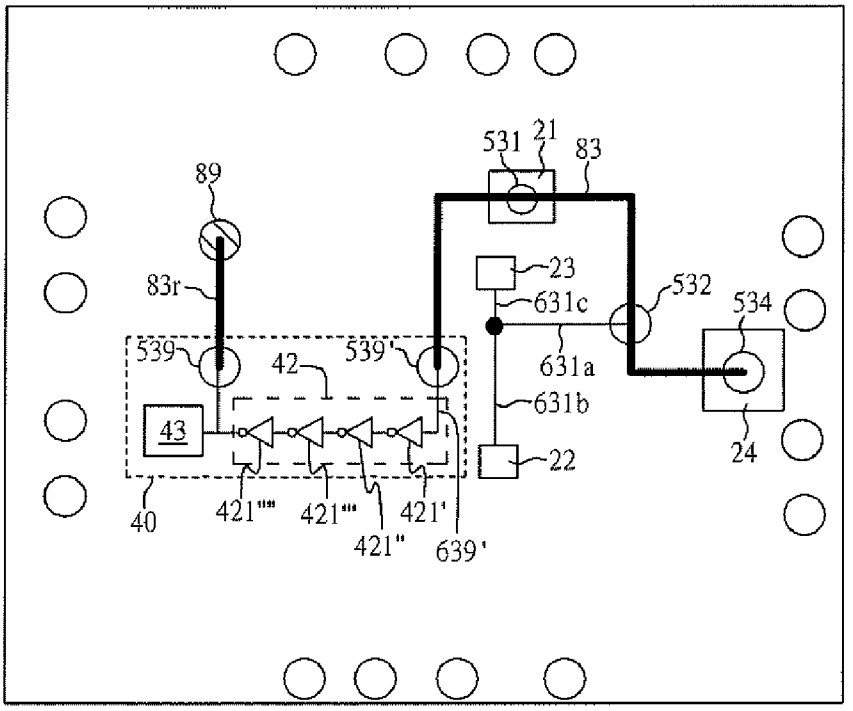


Fig. 9D

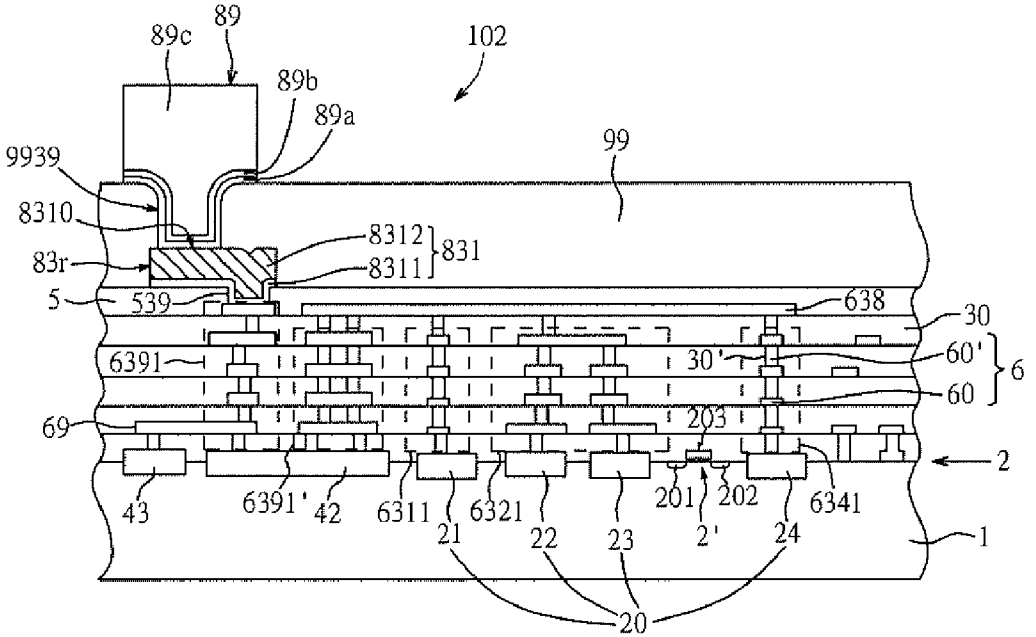


Fig. 10A

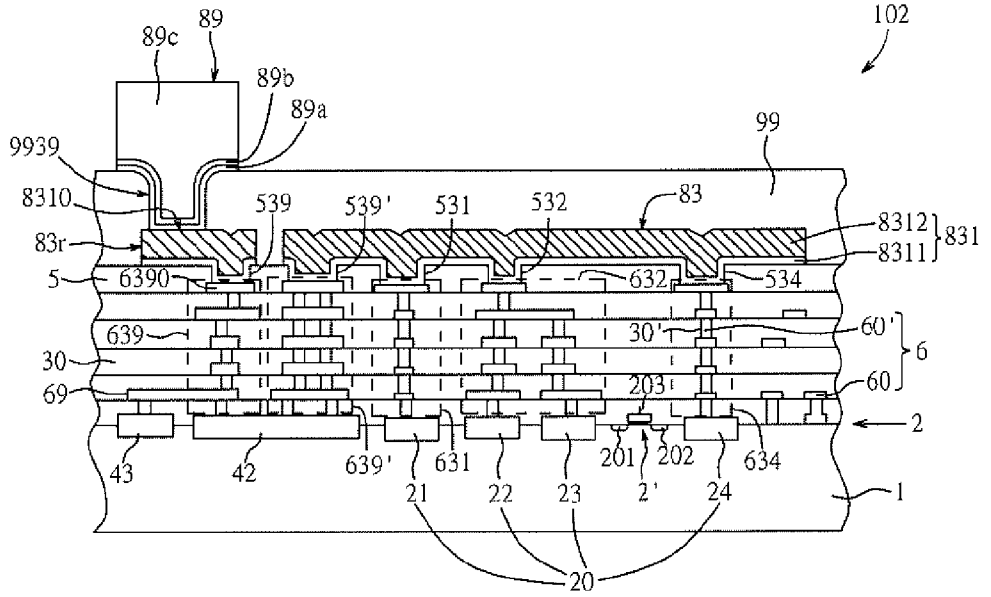


Fig. 10B

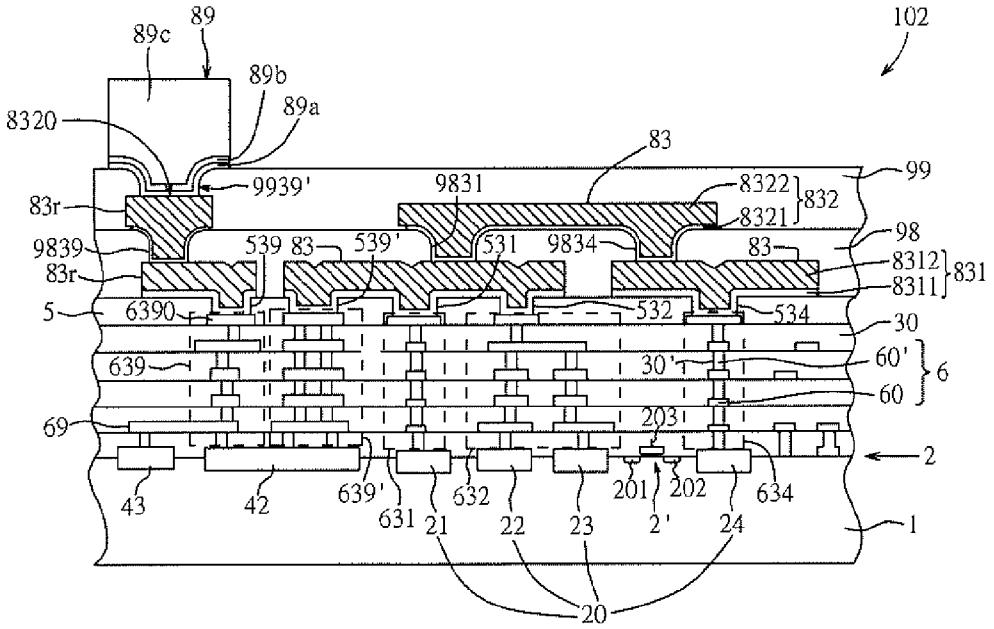


Fig. 10C

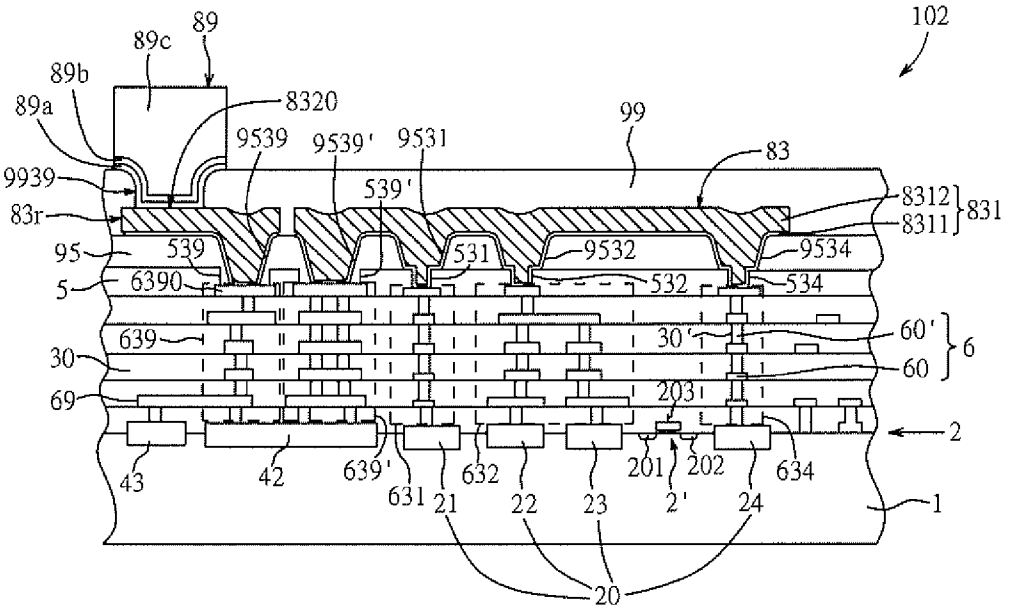


Fig. 10D

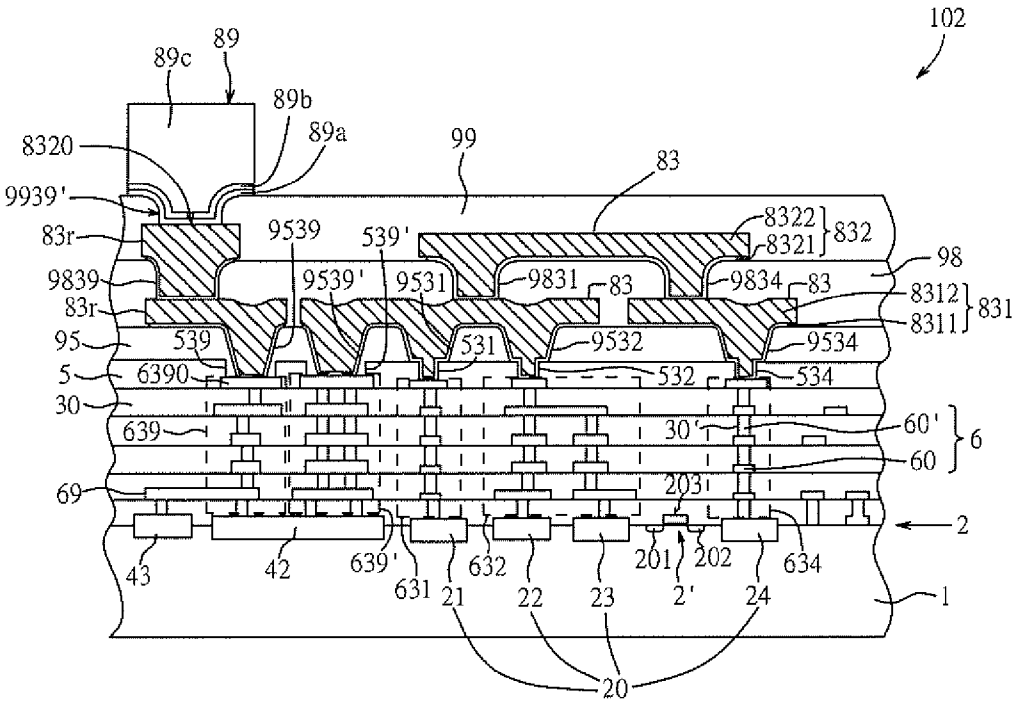


Fig. 10E

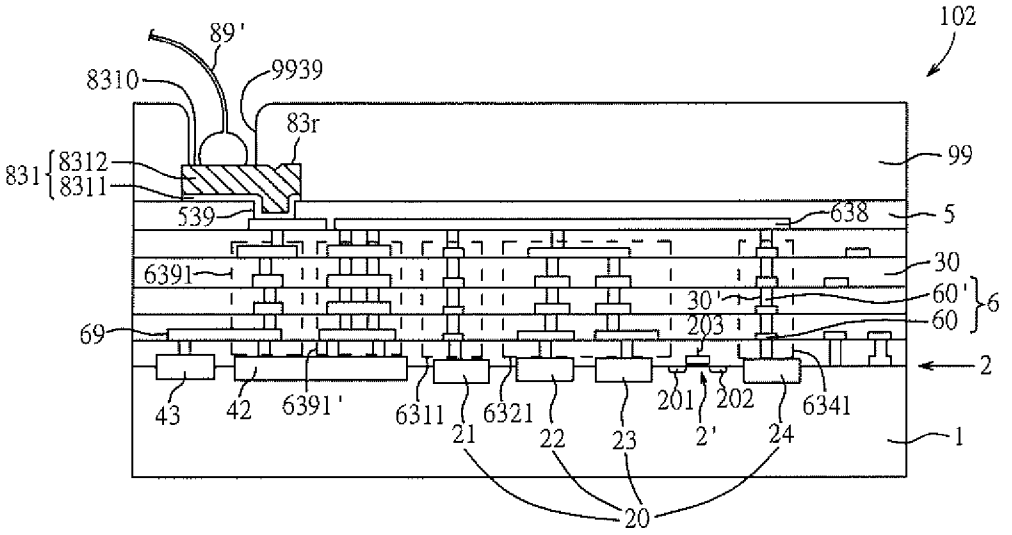


Fig. 10F

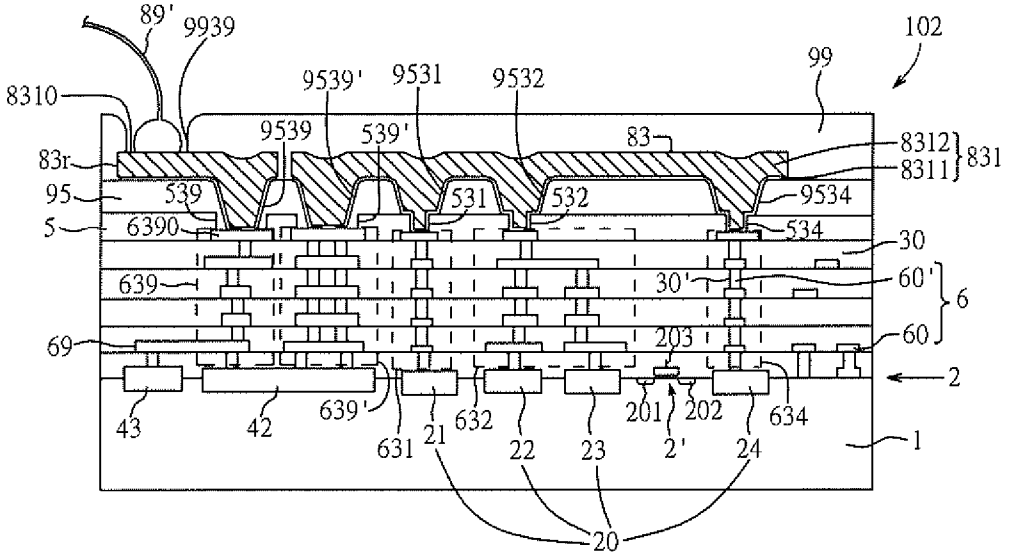


Fig. 10G

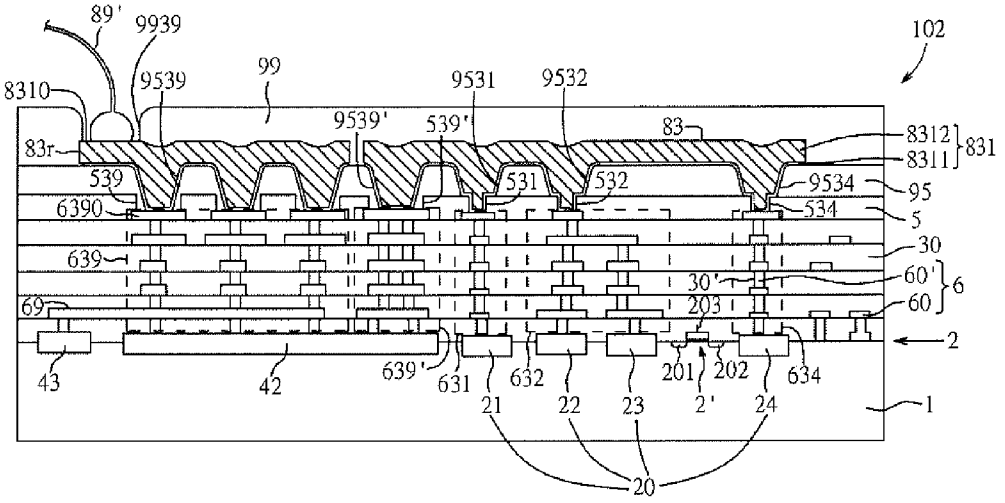


Fig. 10H

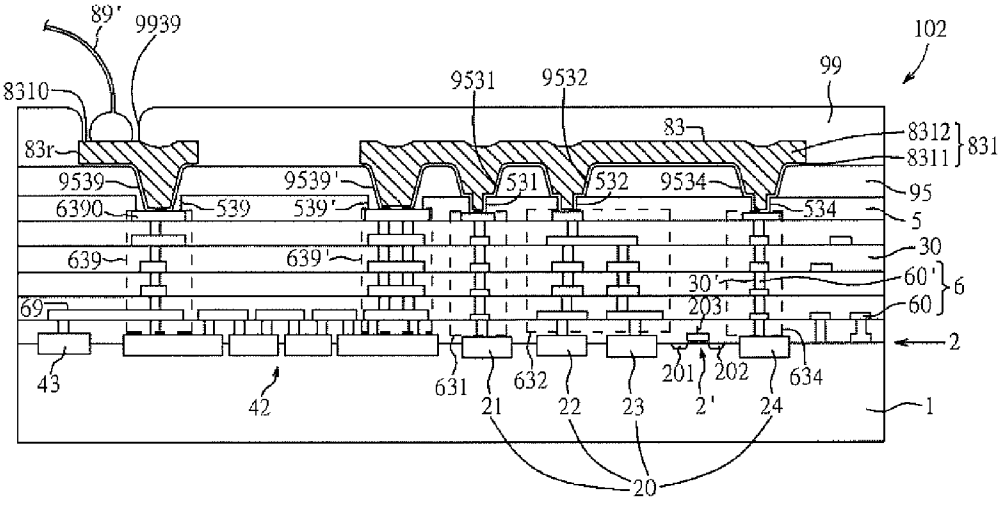


Fig. 10I

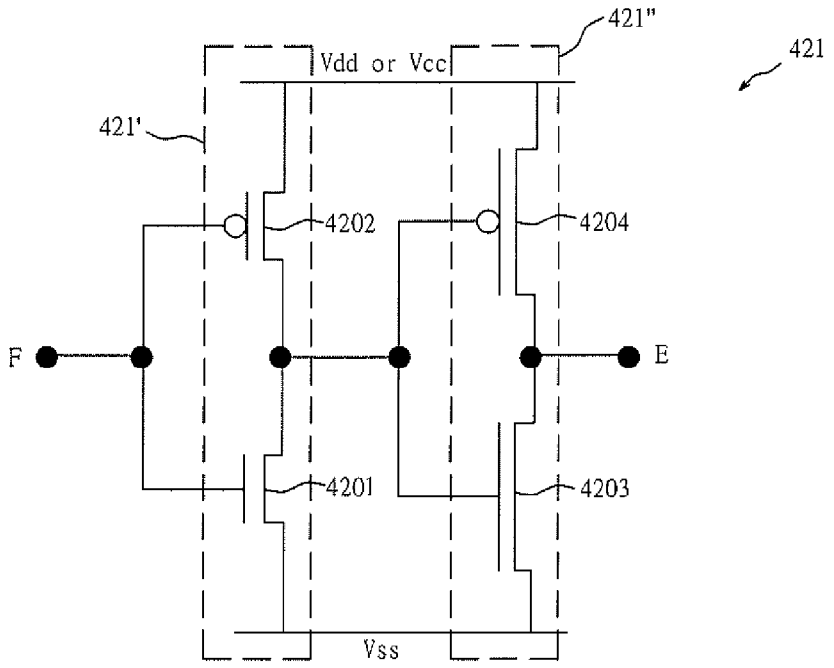


Fig. 11A

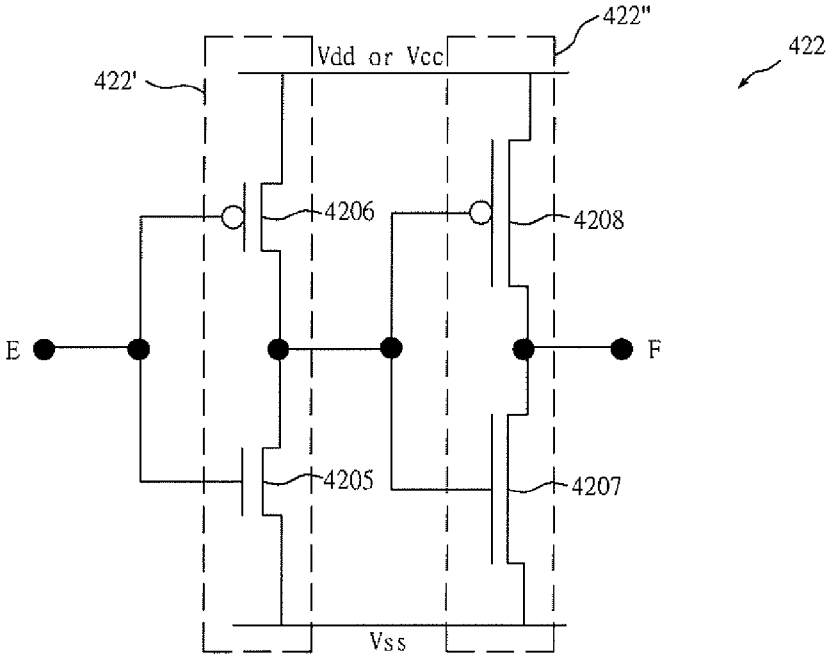


Fig. 11B

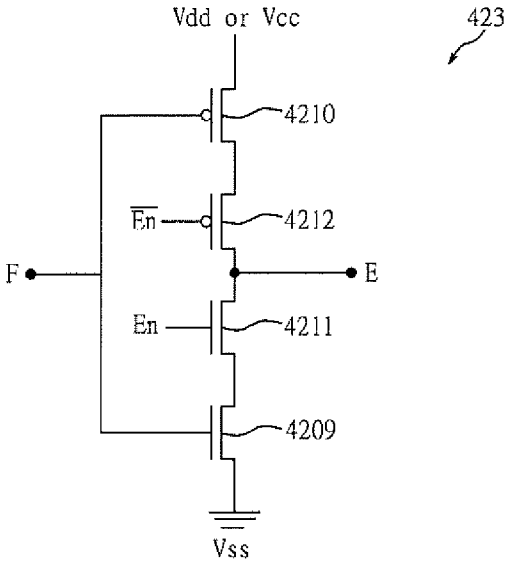


Fig. 11C

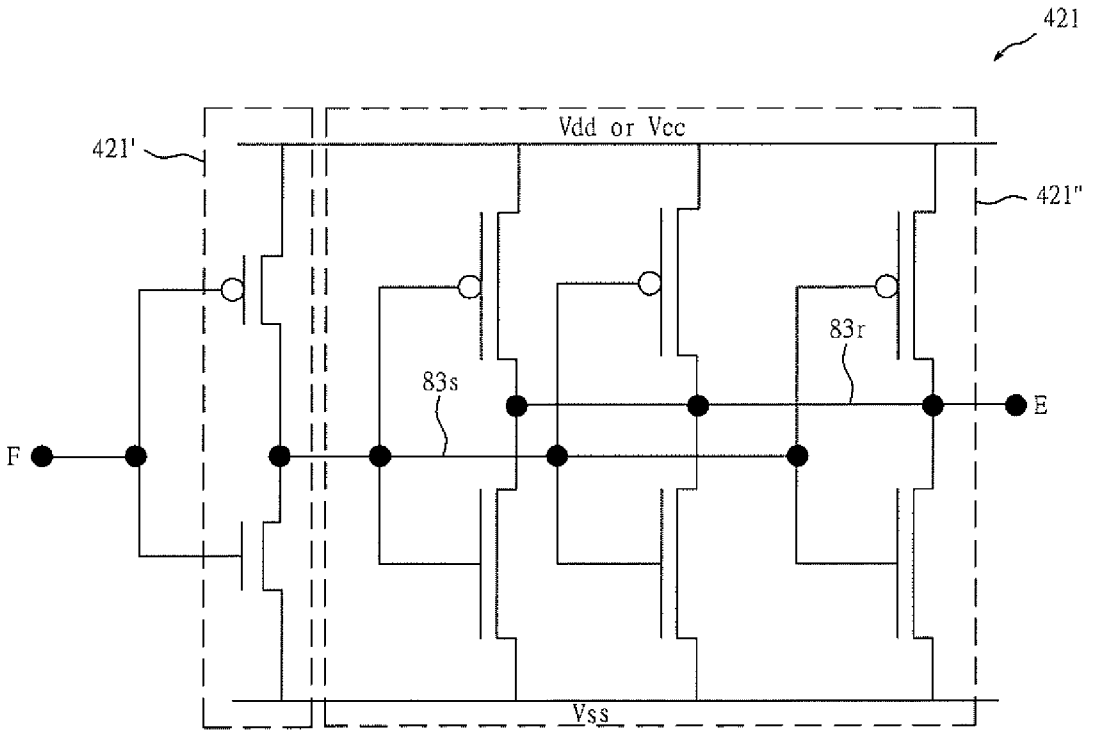


Fig. 11D

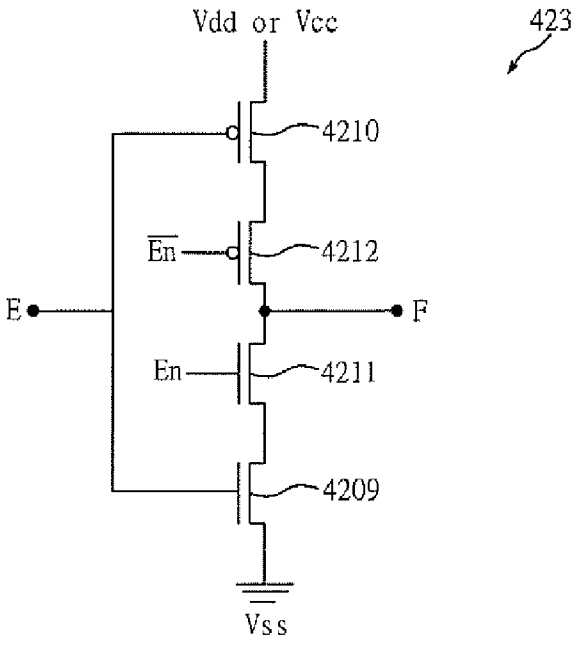


Fig. 11E

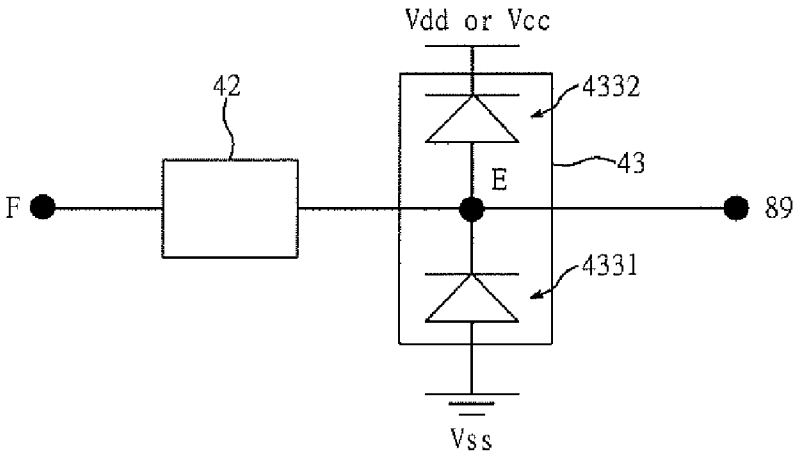


Fig. 11F

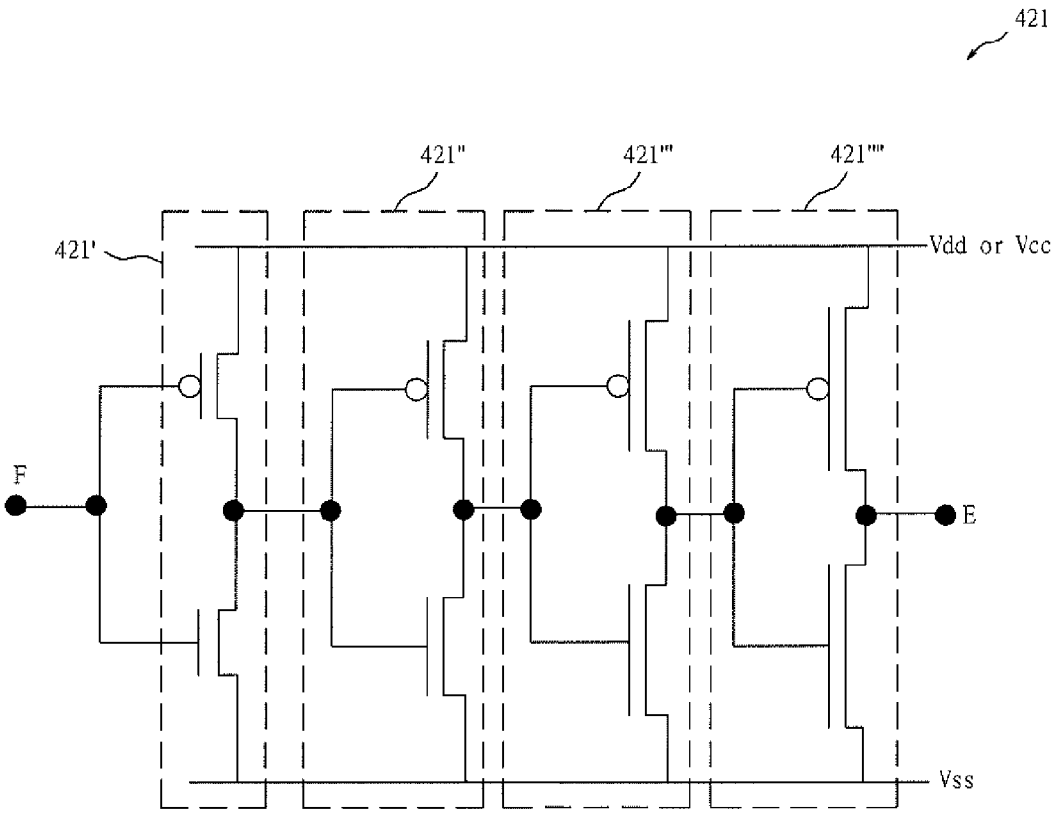


Fig. 11G

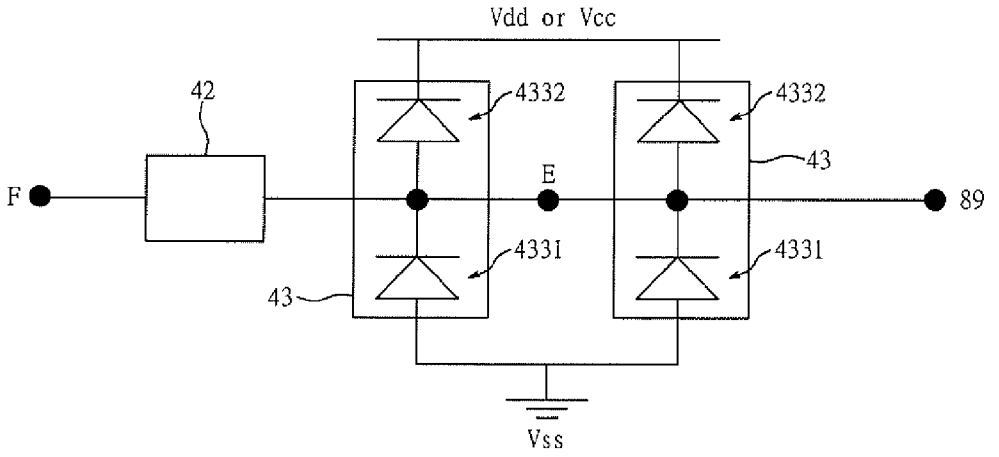


Fig. 11H

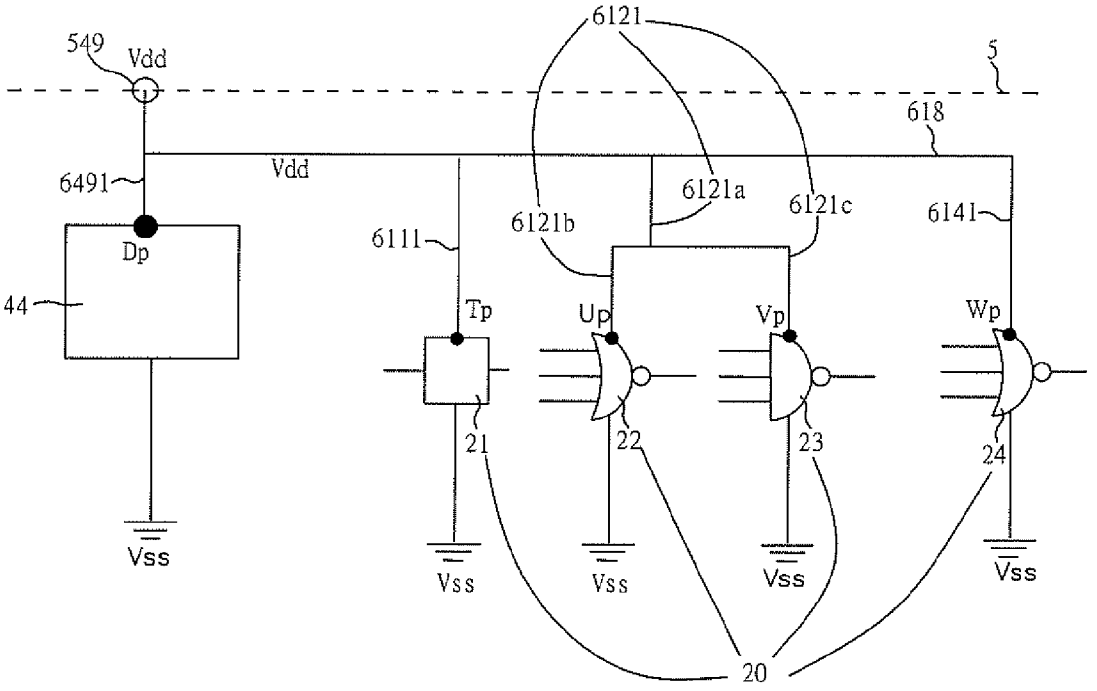


Fig. 12A

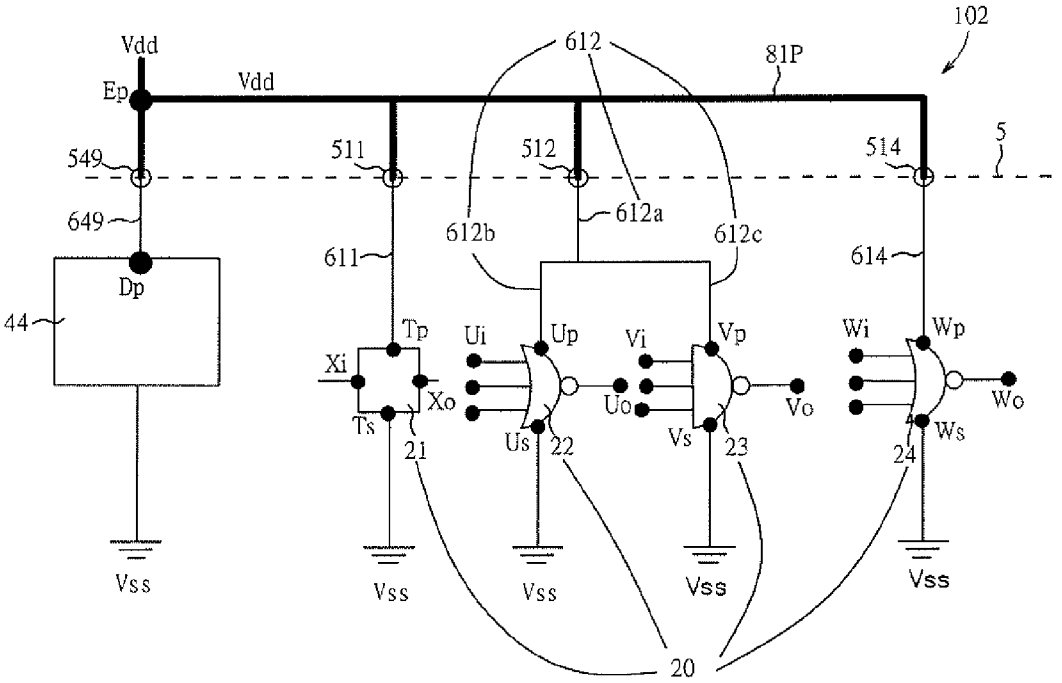


Fig. 12B

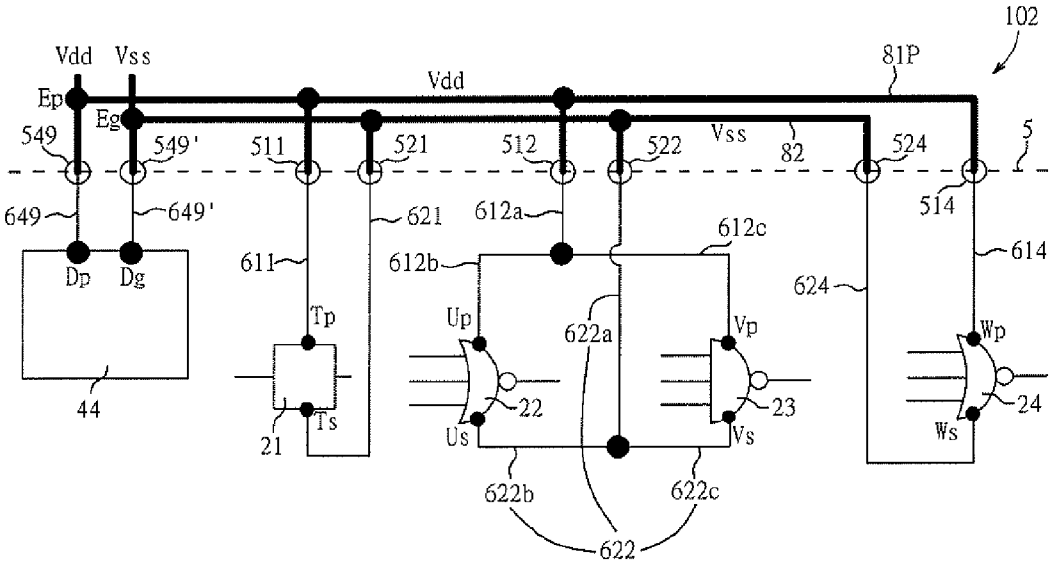


Fig. 12C

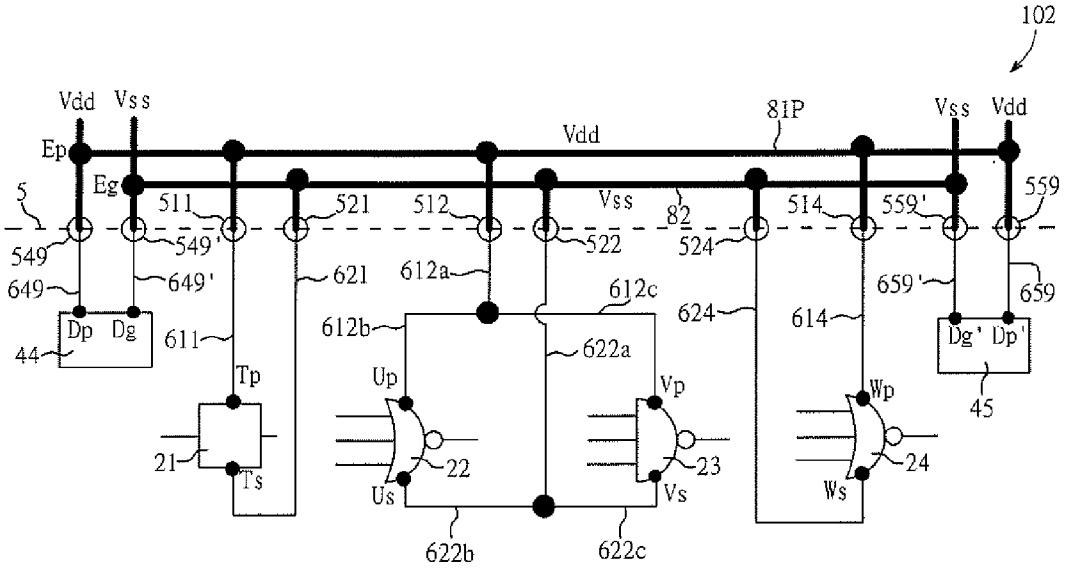


Fig. 12D

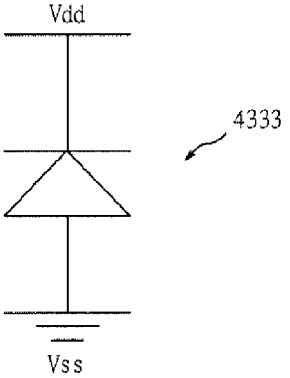


Fig. 12E

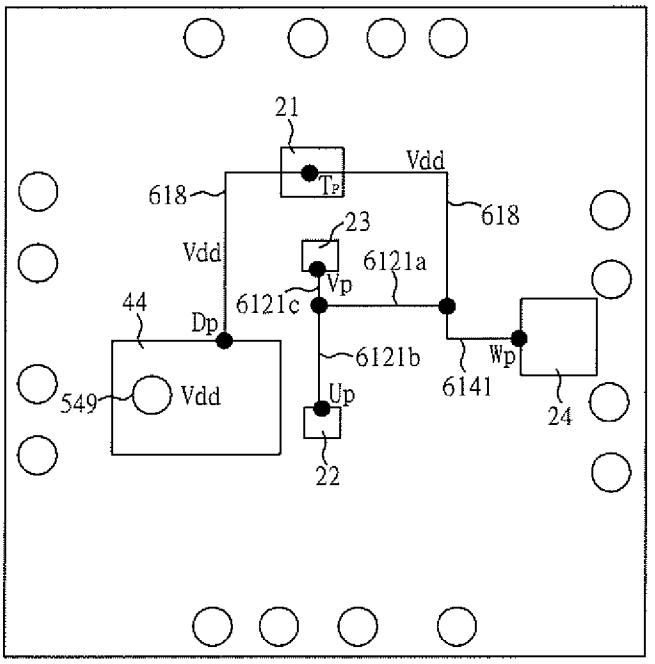


Fig. 13A

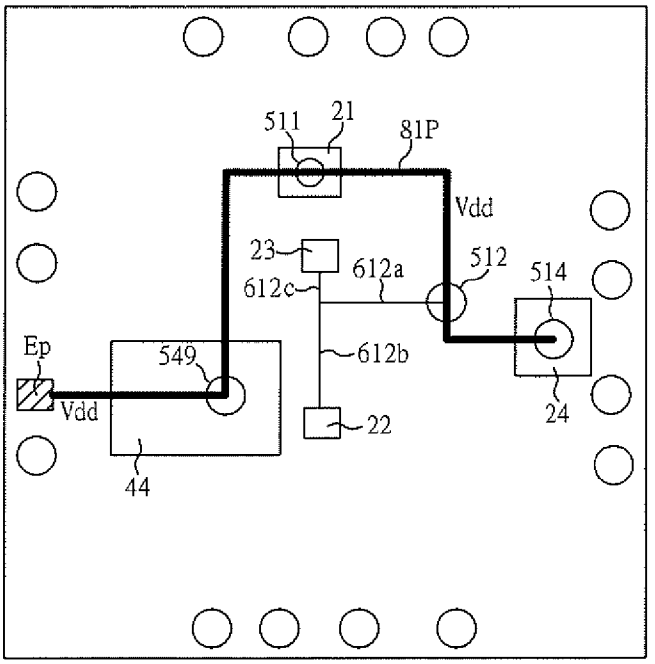


Fig. 13B

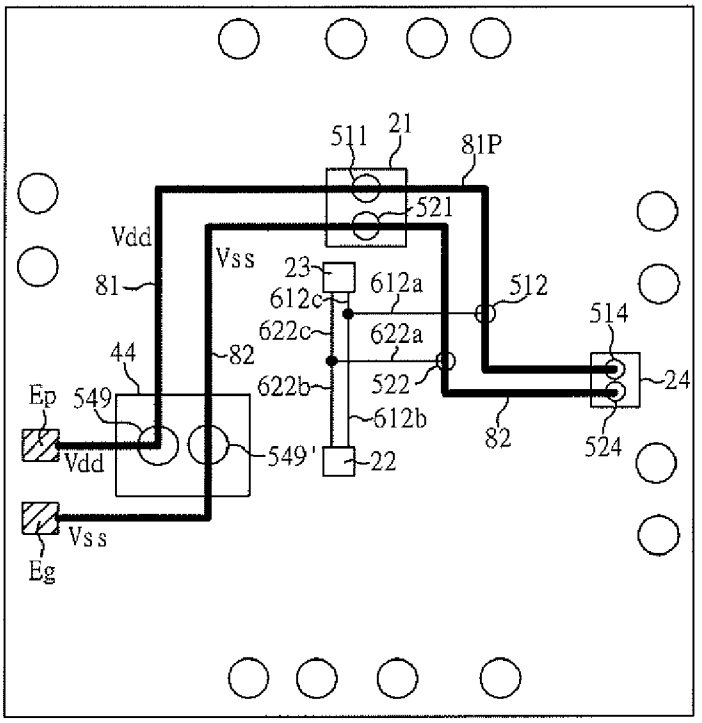


Fig. 13C

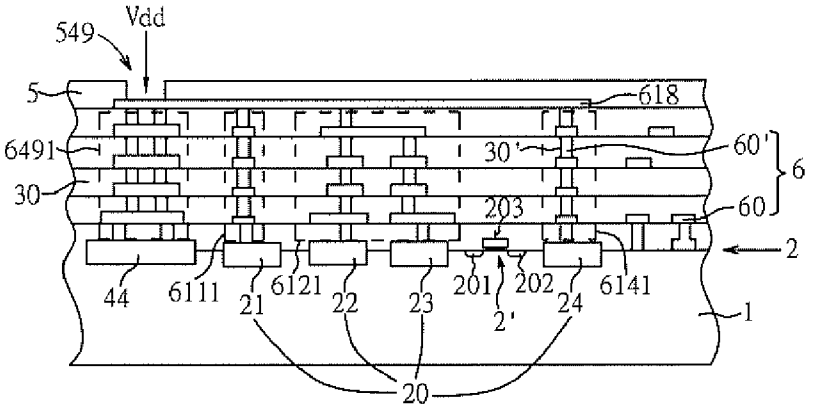


Fig. 14A

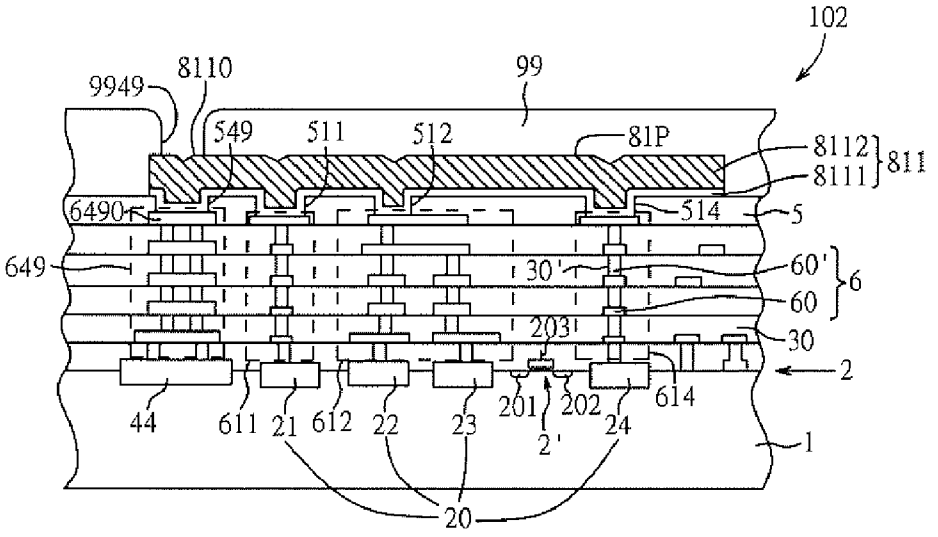


Fig. 14B

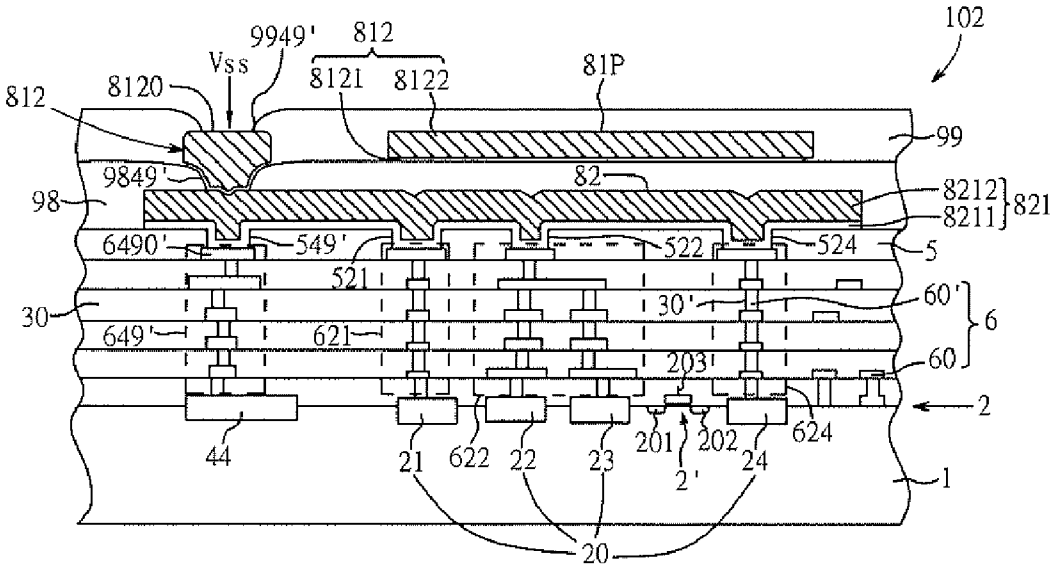


Fig. 14C

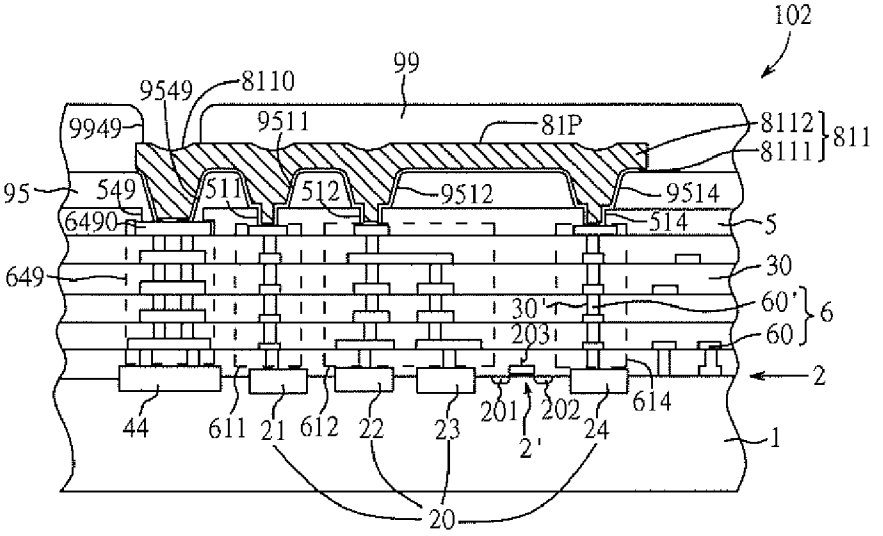


Fig. 14D

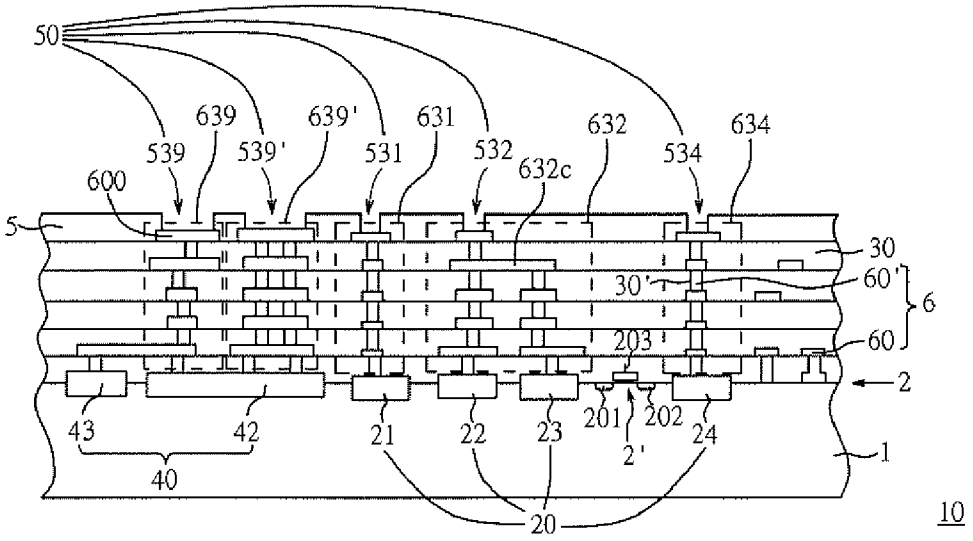


Fig. 15A

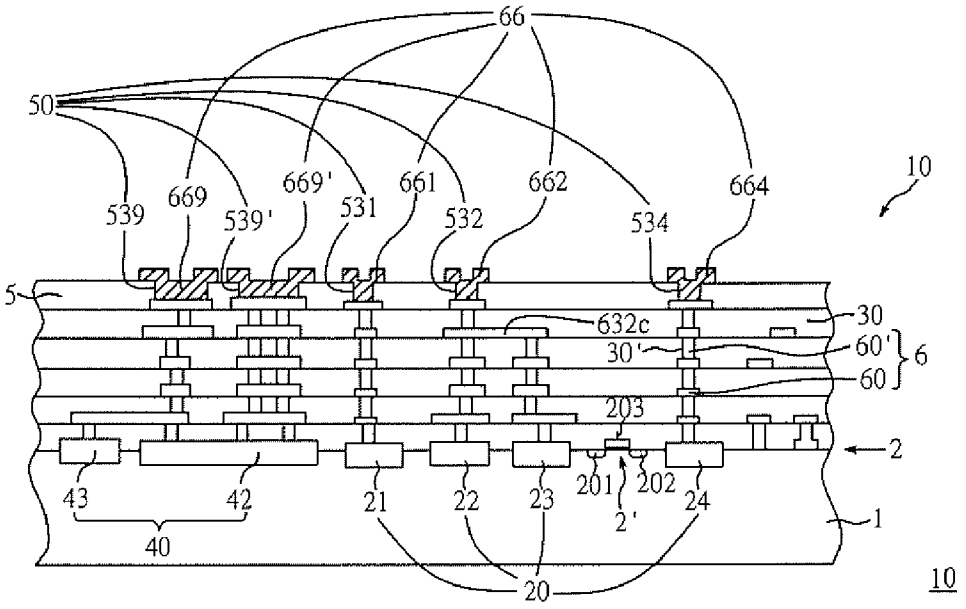


Fig. 15B

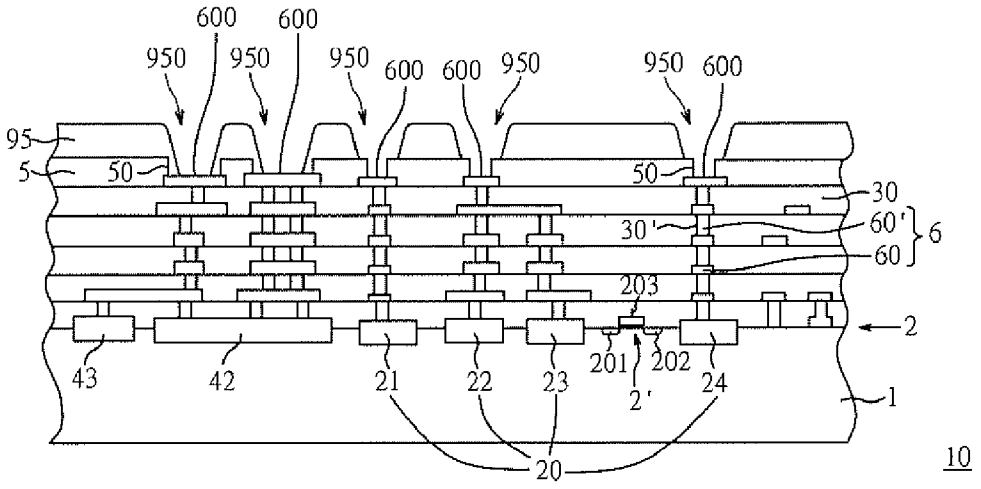


Fig. 15C

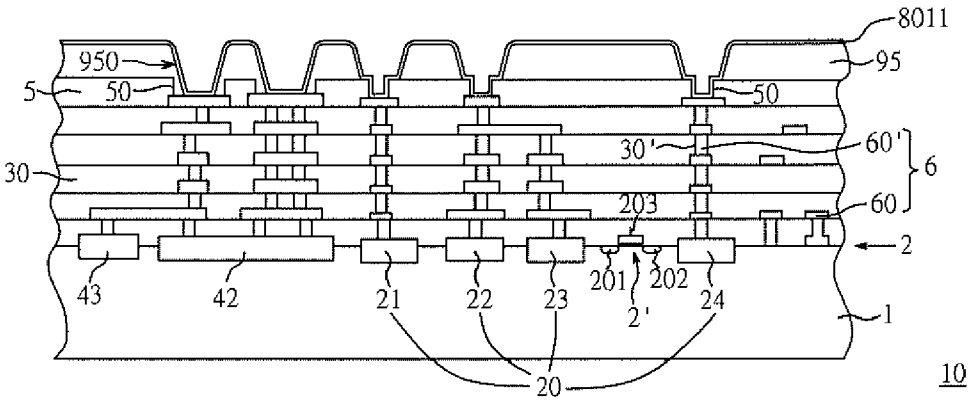


Fig. 15D

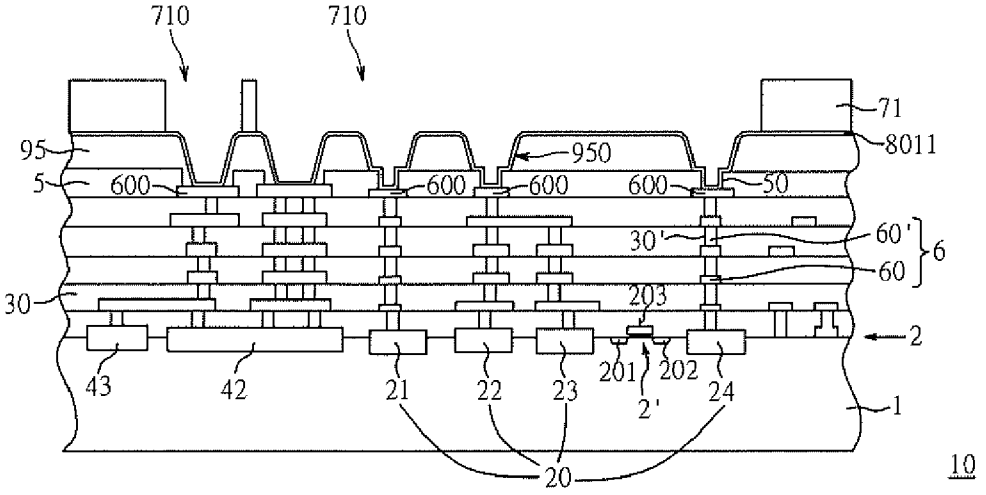


Fig. 15E

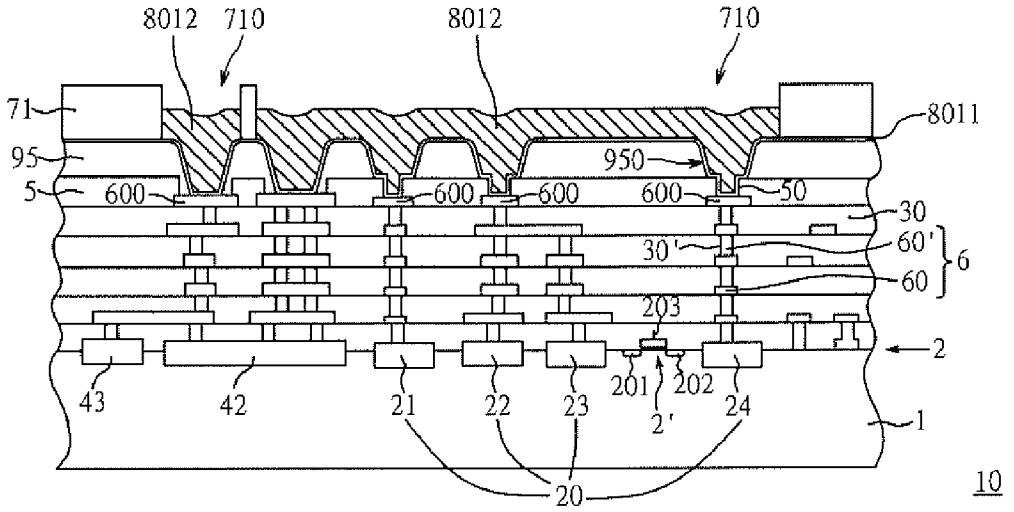


Fig. 15F

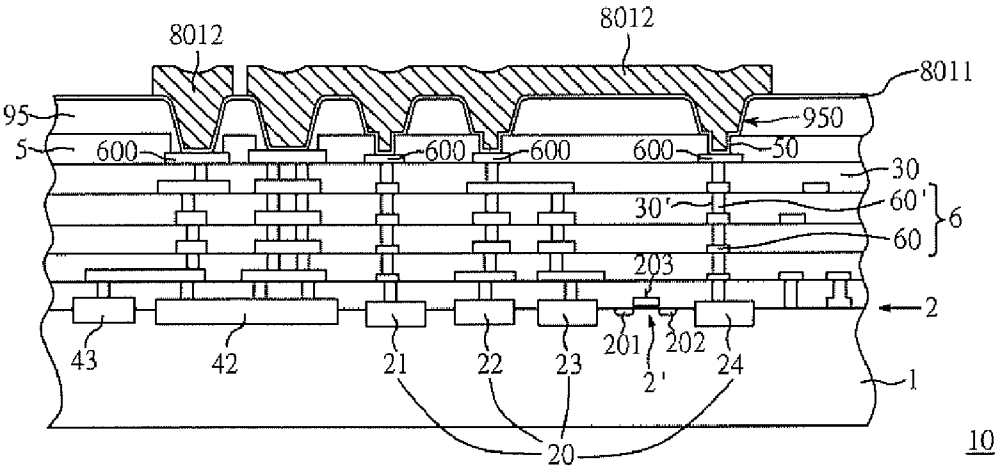


Fig. 15G

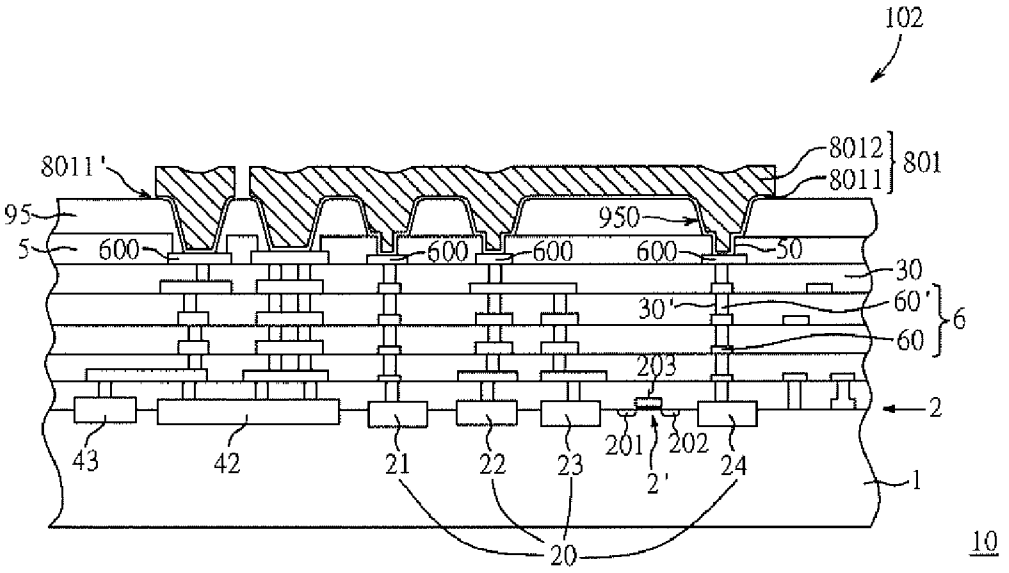


Fig. 15H

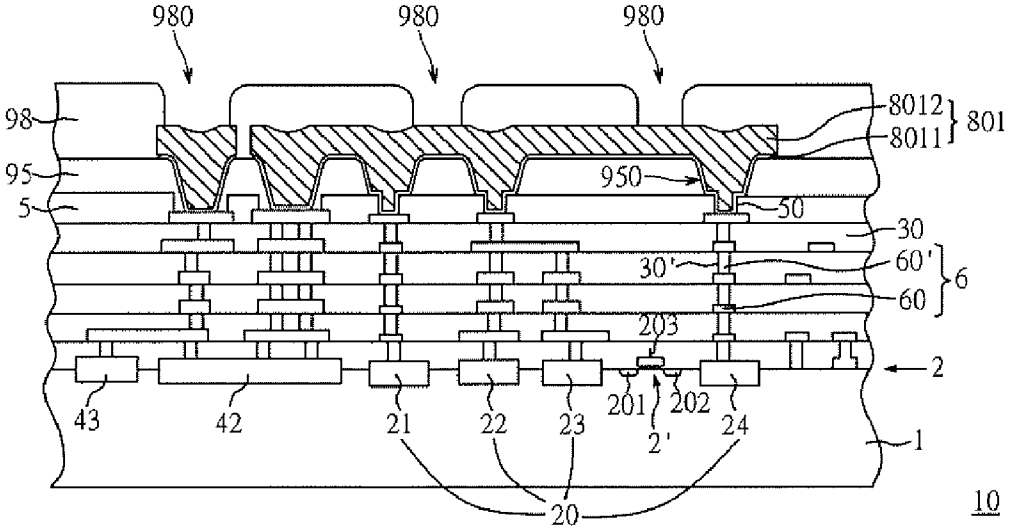


Fig. 15I

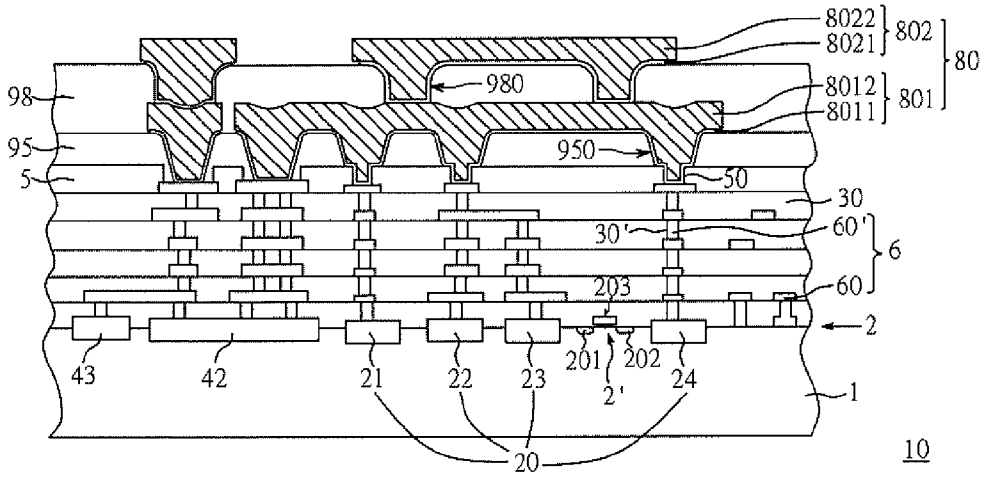


Fig. 15J

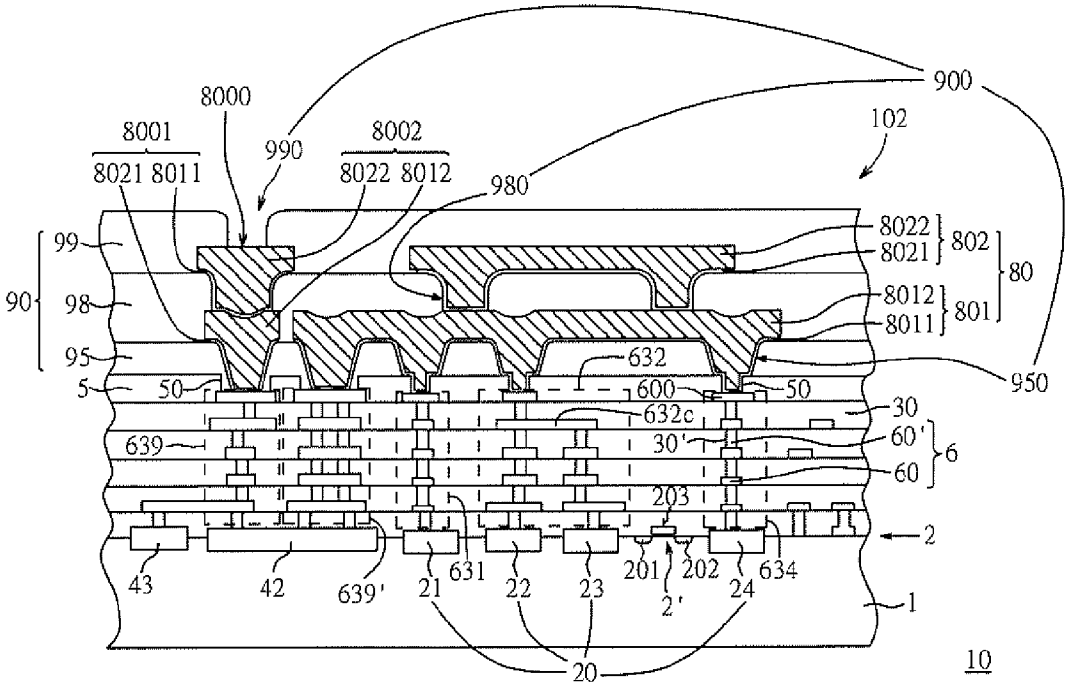


Fig. 15K

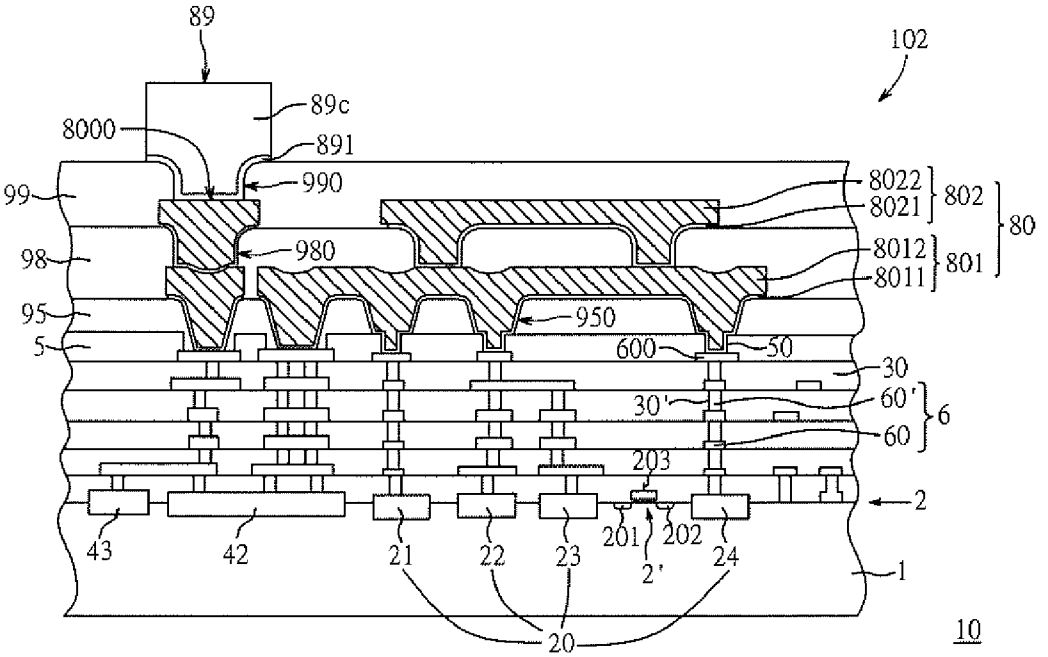


Fig. 15L

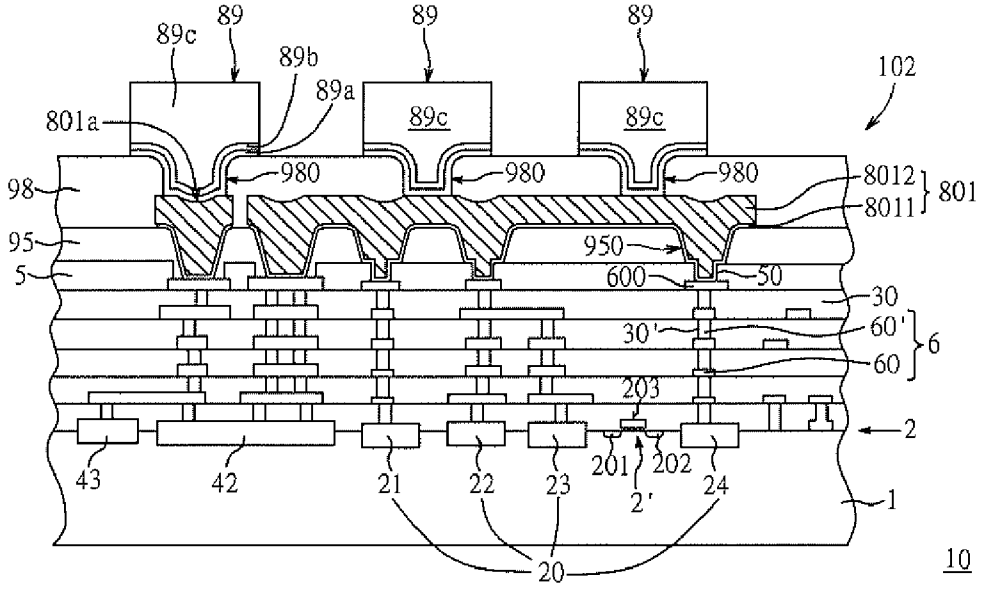


Fig. 15M

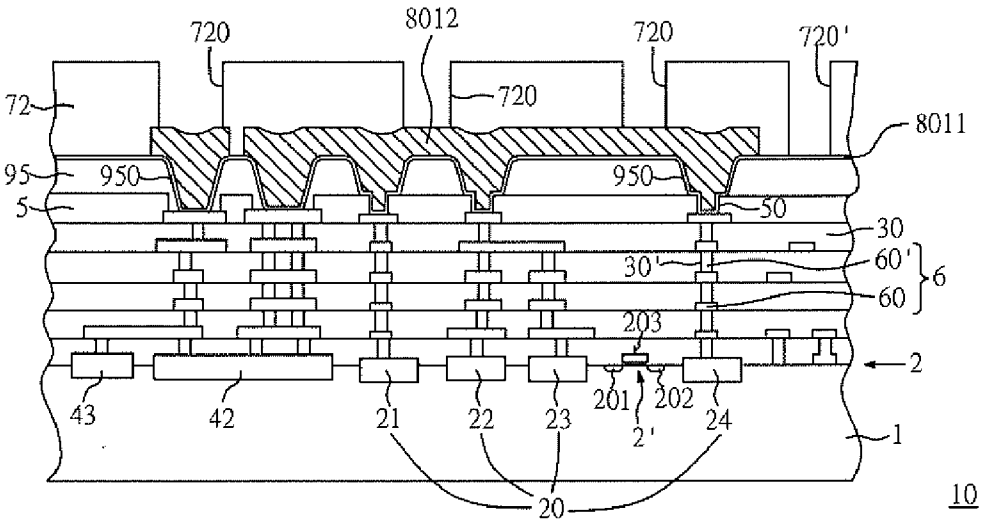


Fig. 16A

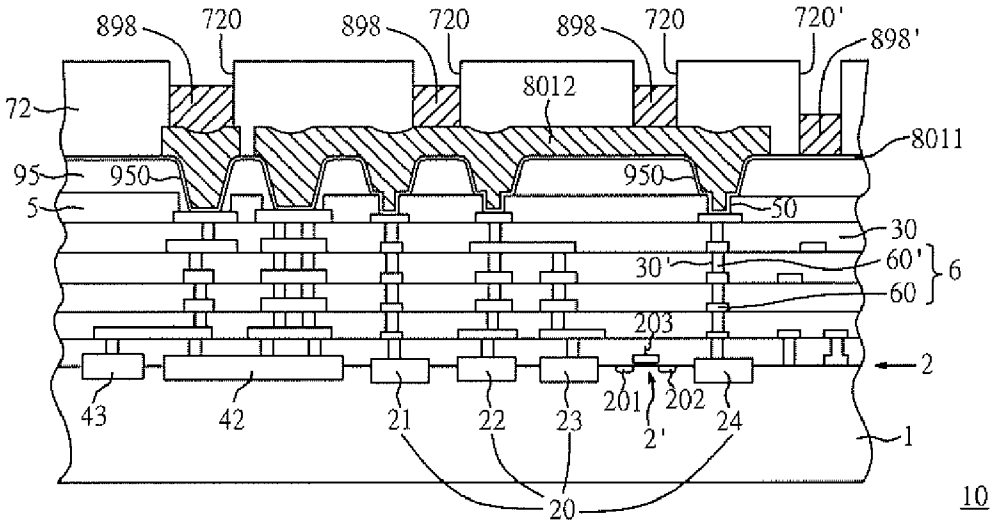


Fig. 16B

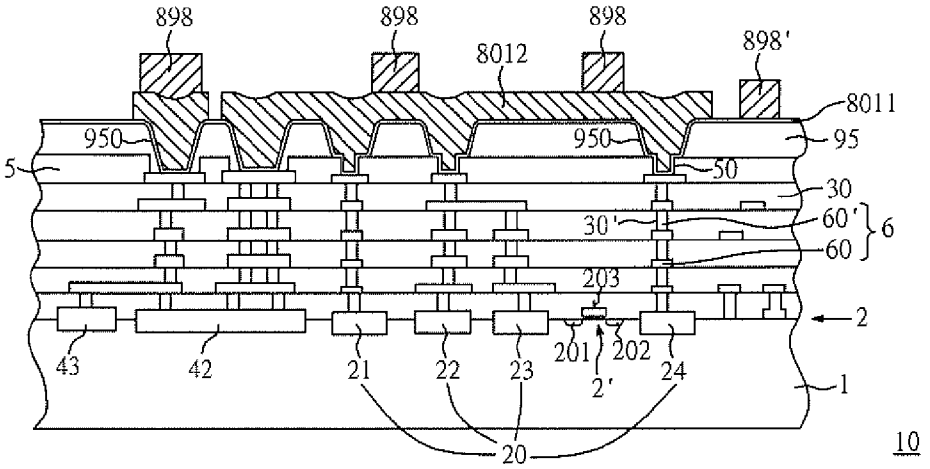


Fig. 16C

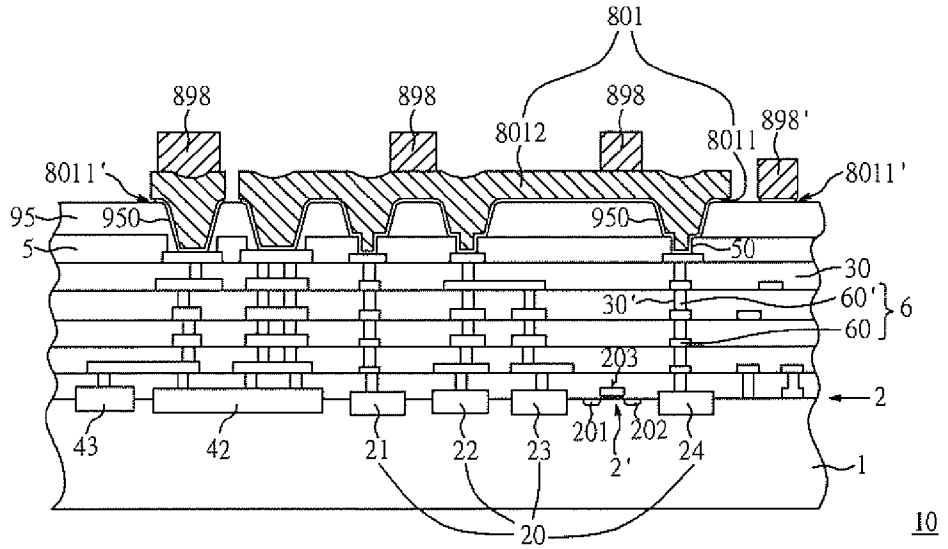


Fig. 16D

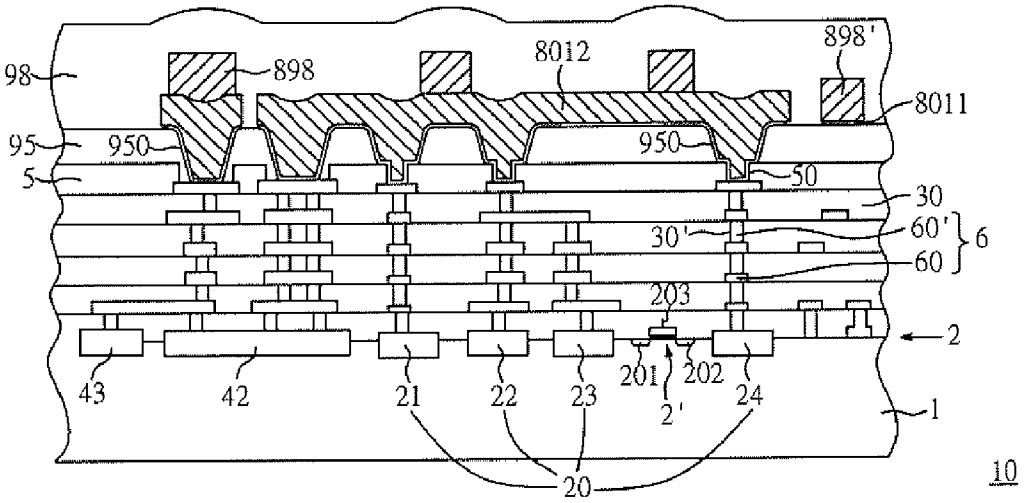


Fig. 16E

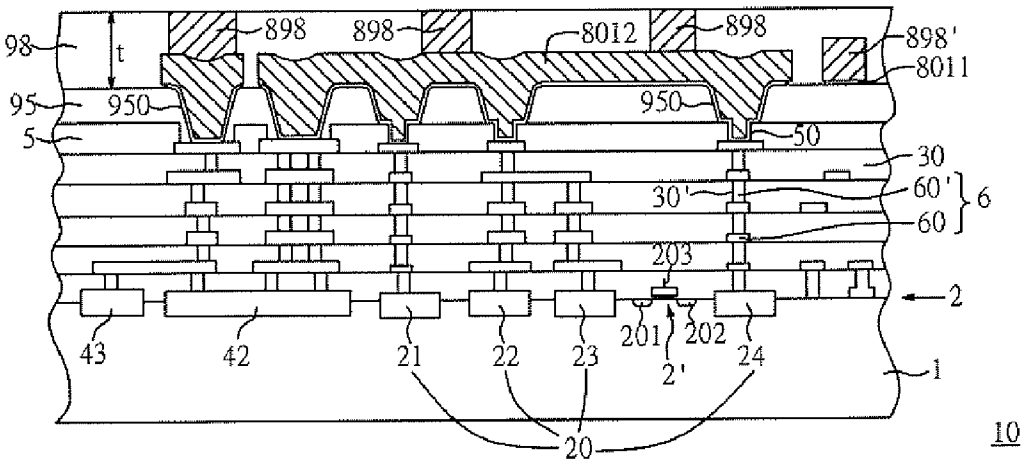


Fig. 16F

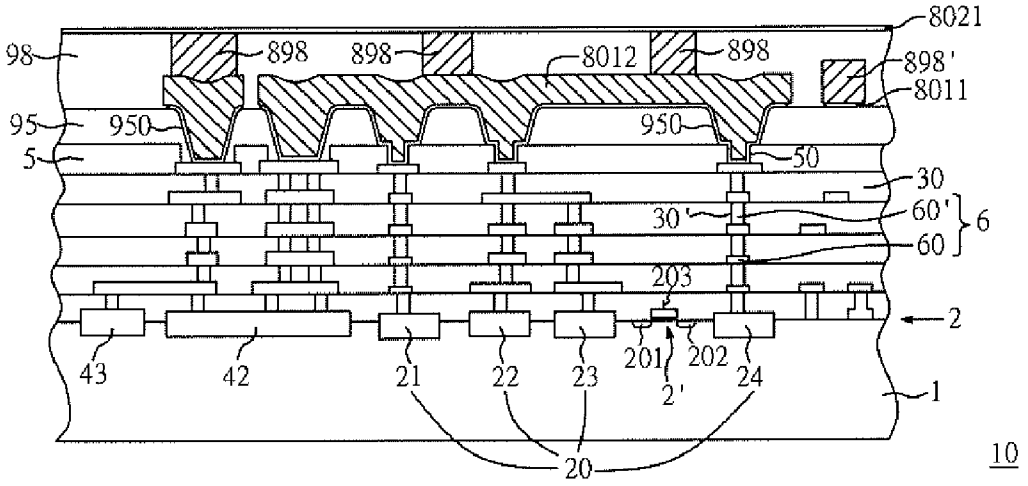


Fig. 16G

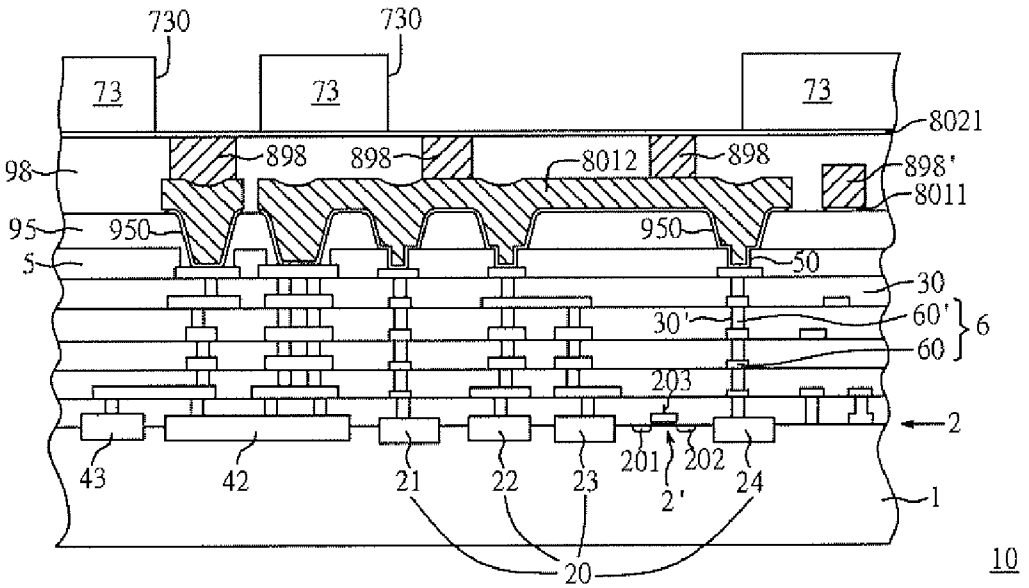


Fig. 16H

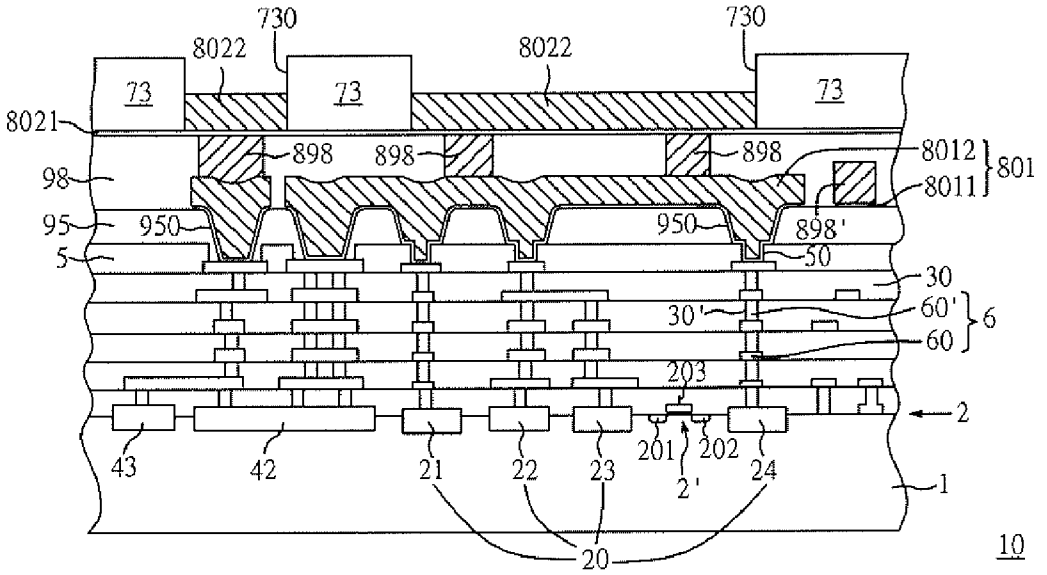


Fig. 16I

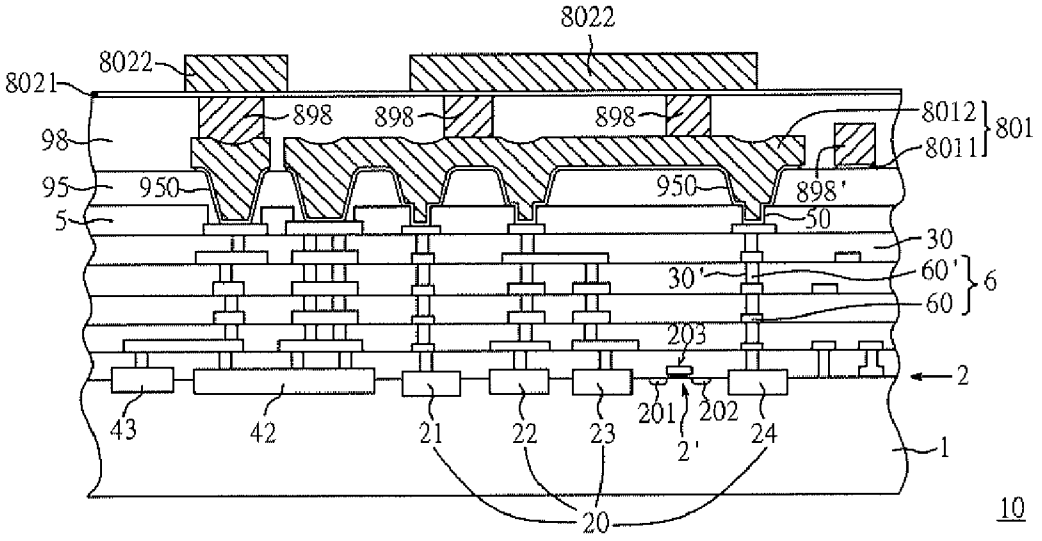


Fig. 16J

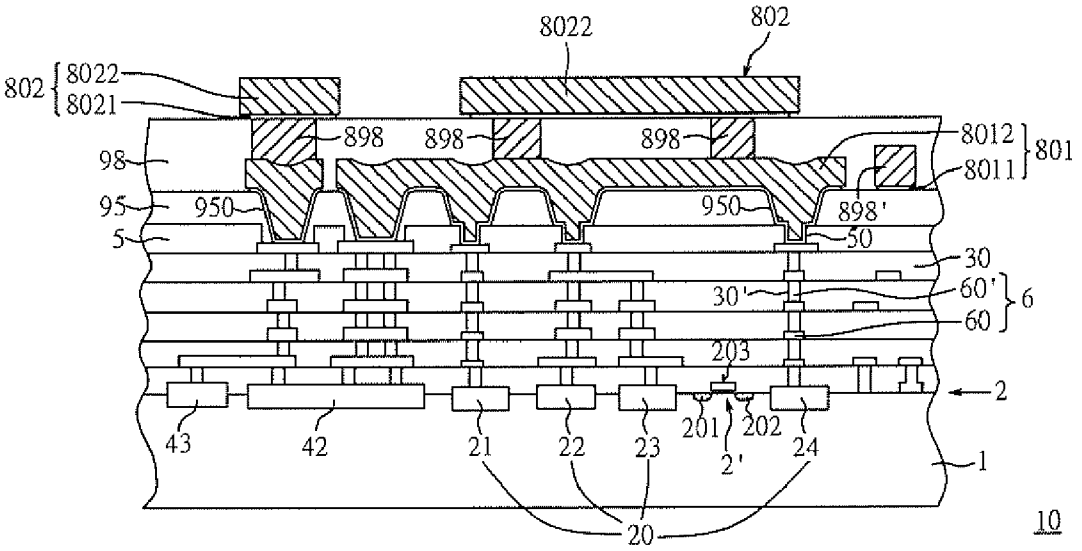


Fig. 16K

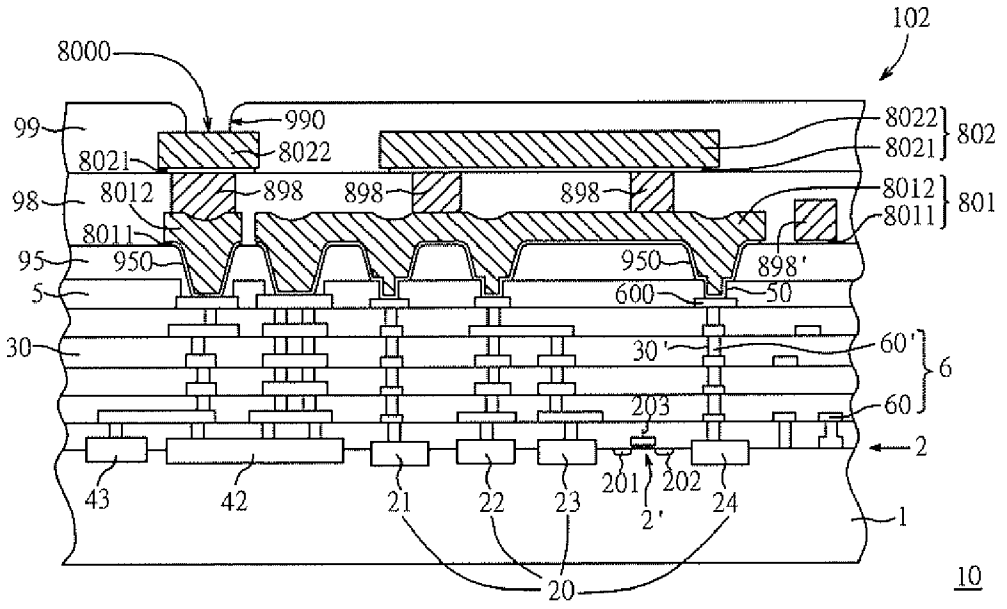


Fig. 16L

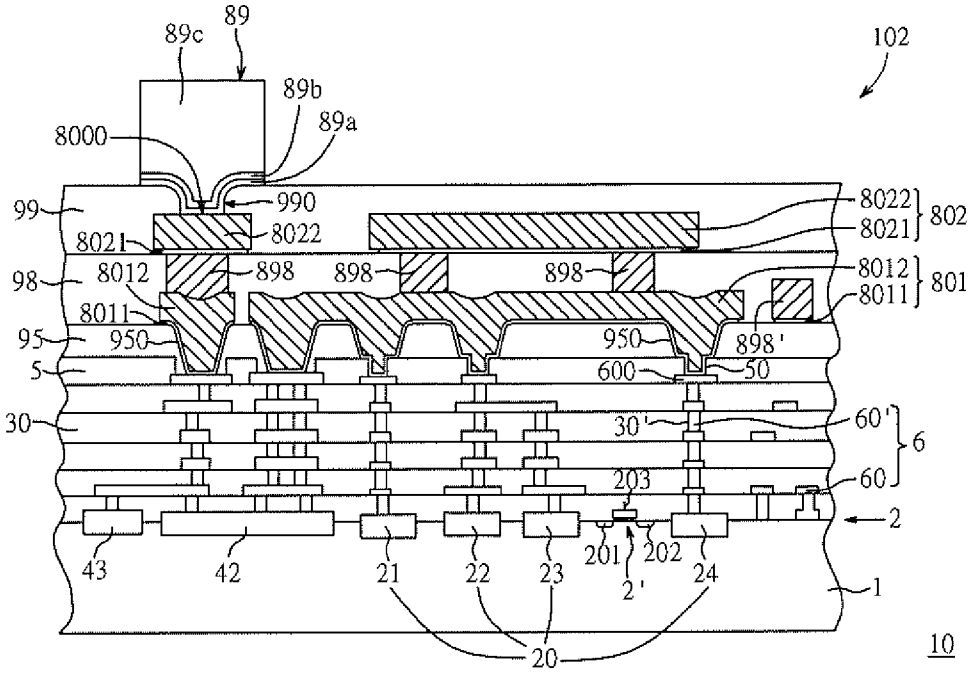


Fig. 16M

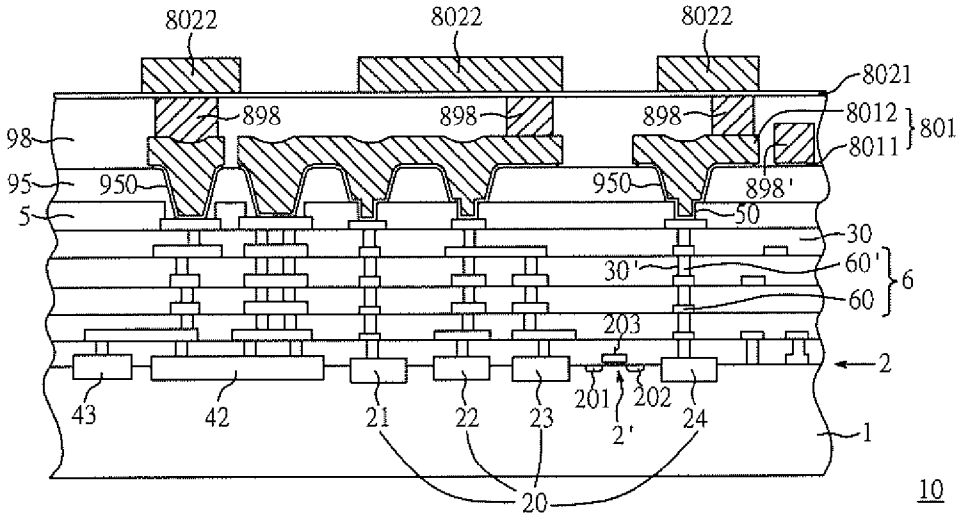


Fig. 17A

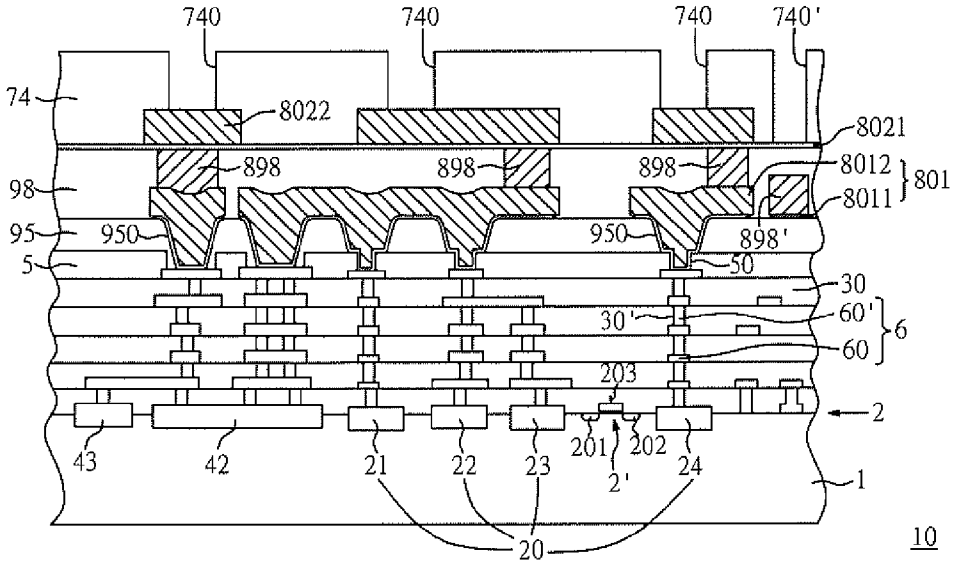


Fig. 17B

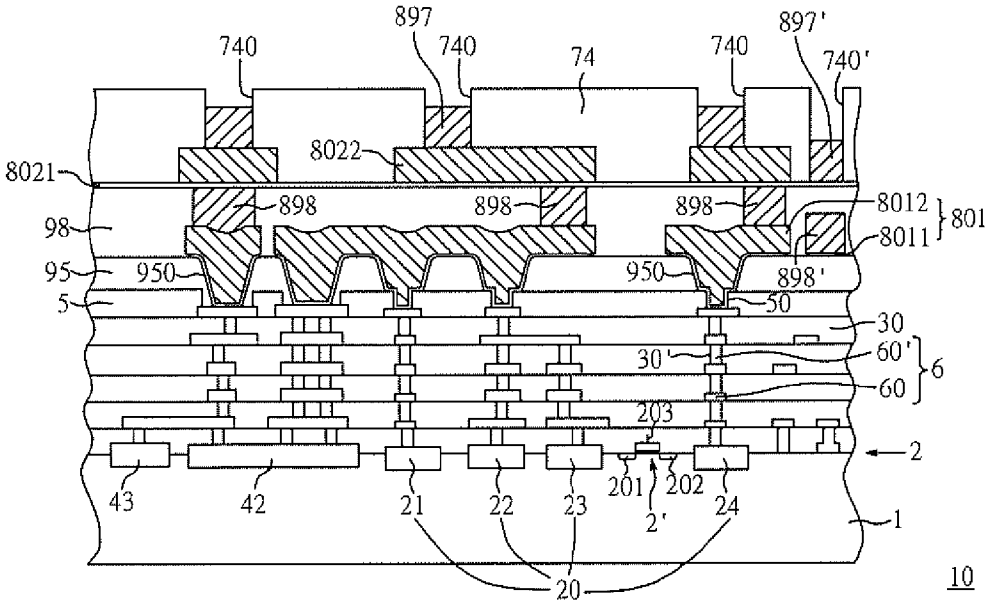


Fig. 17C

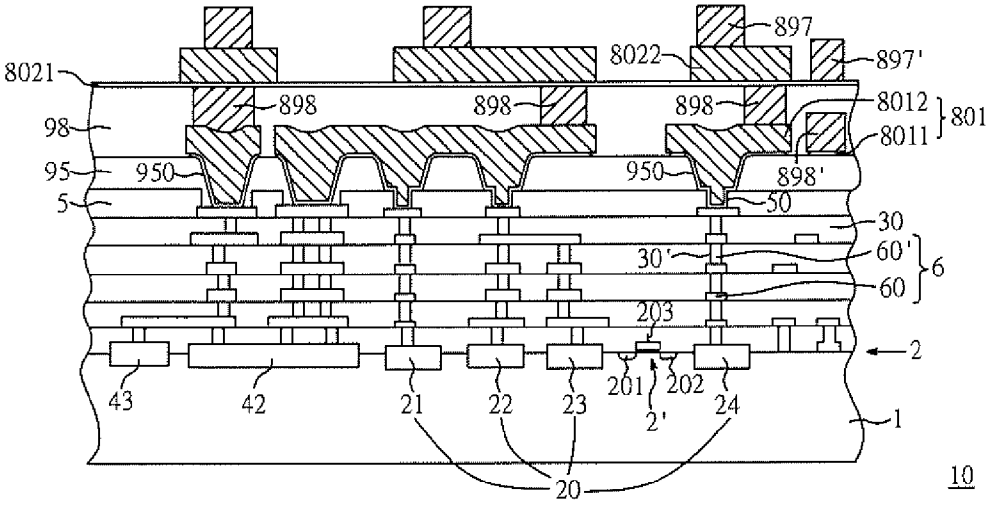


Fig. 17D

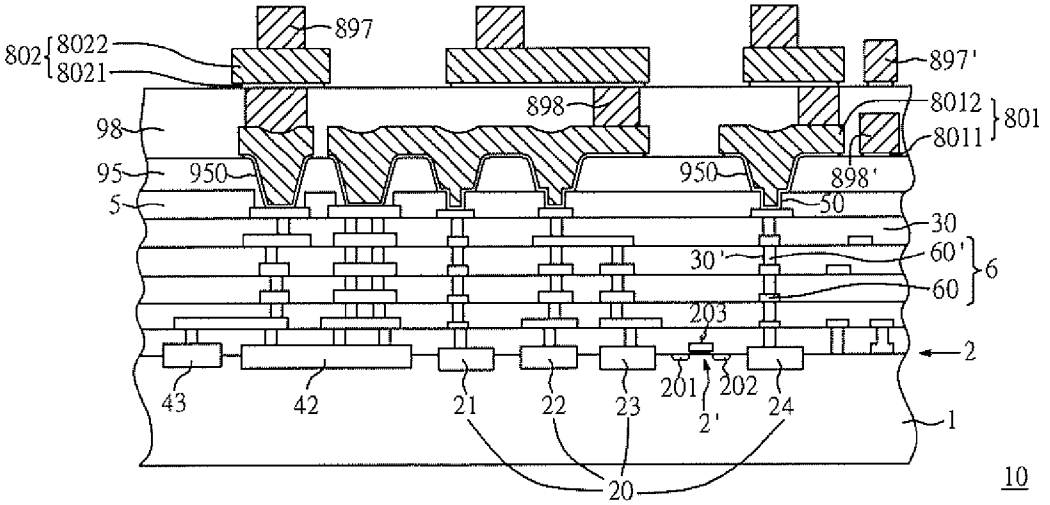


Fig. 17E

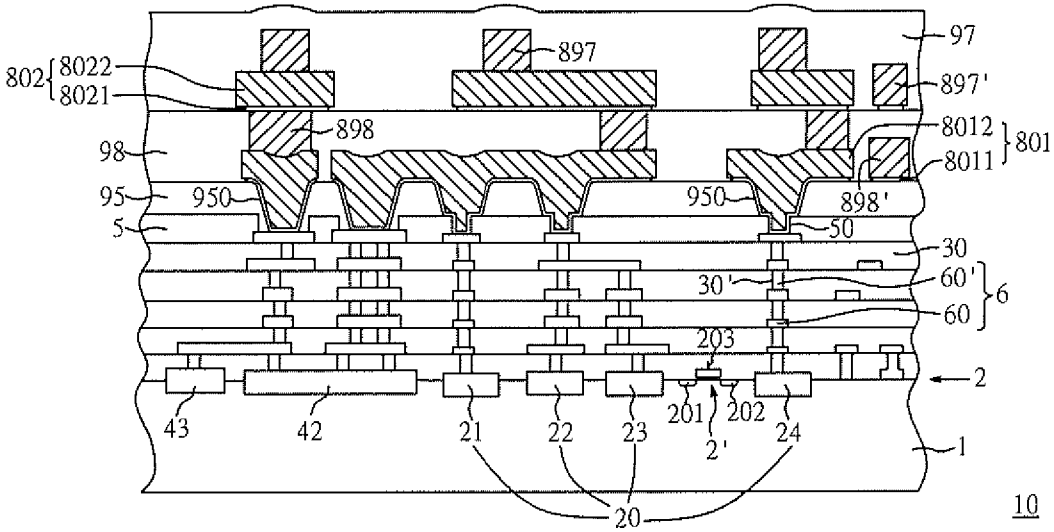


Fig. 17F

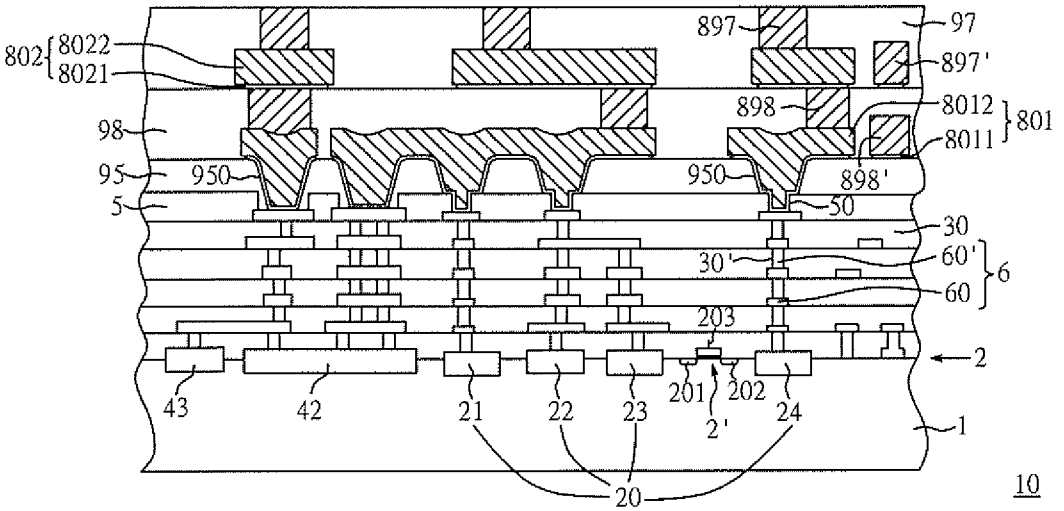


Fig. 17G

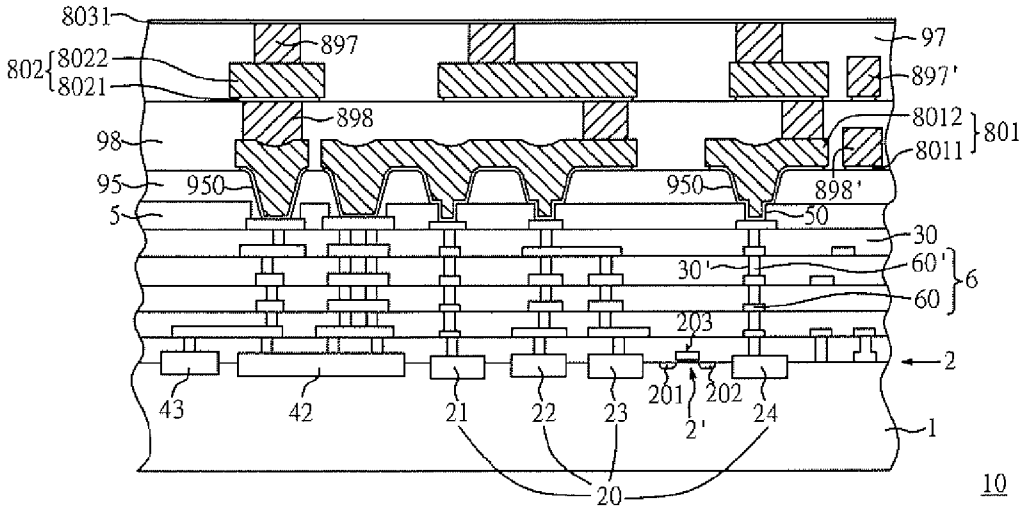


Fig. 17H

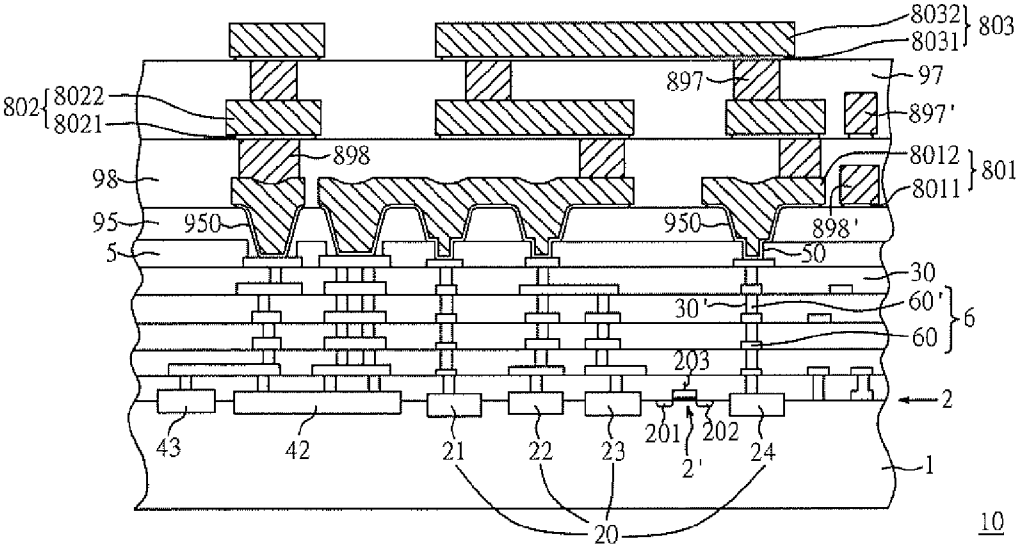


Fig. 17I

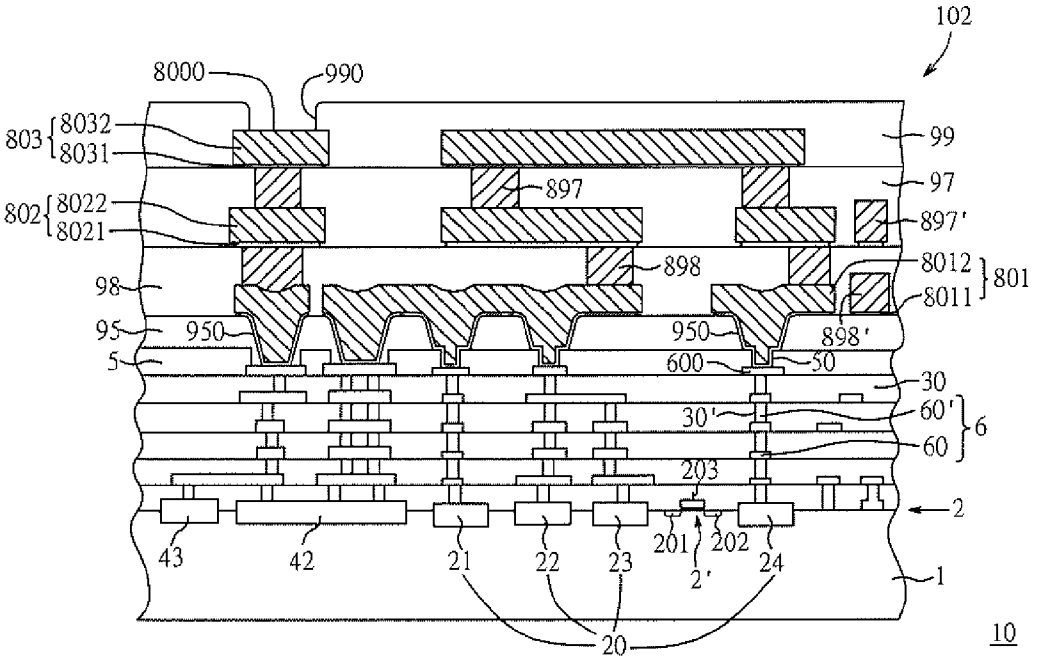


Fig. 17J

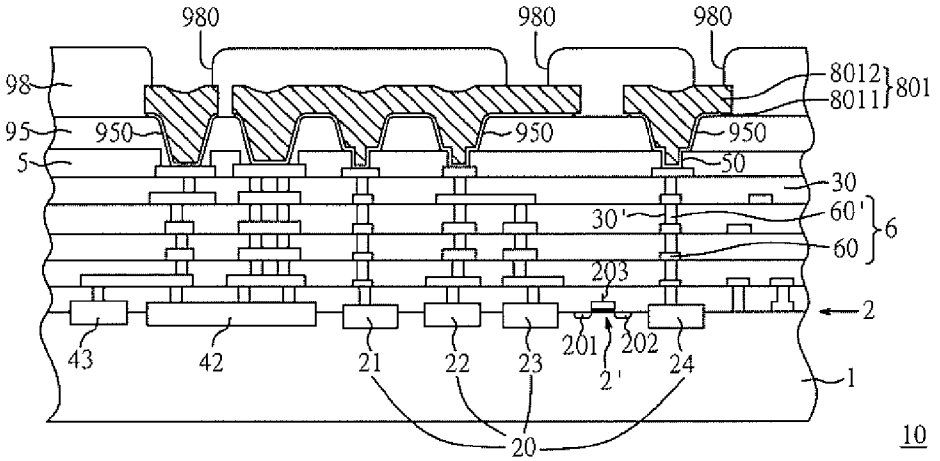


Fig. 18A

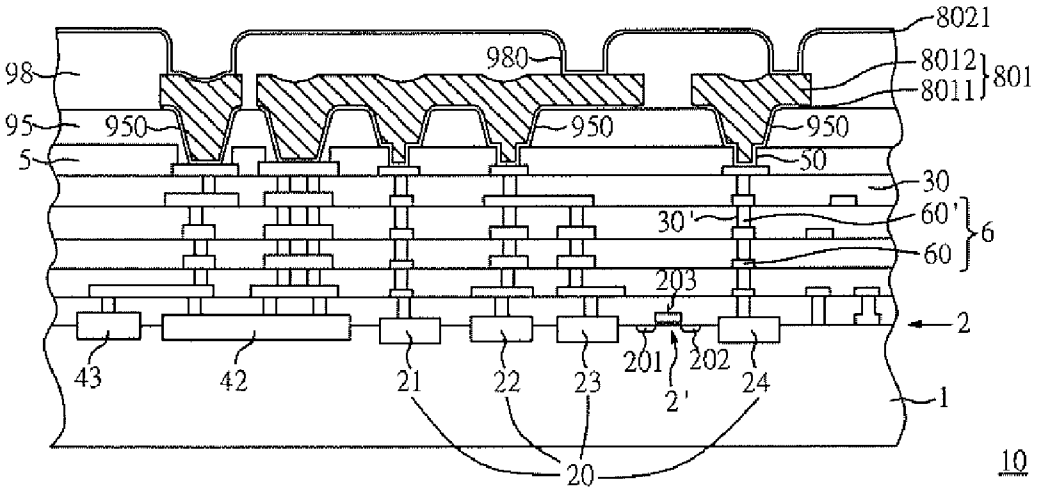


Fig. 18B

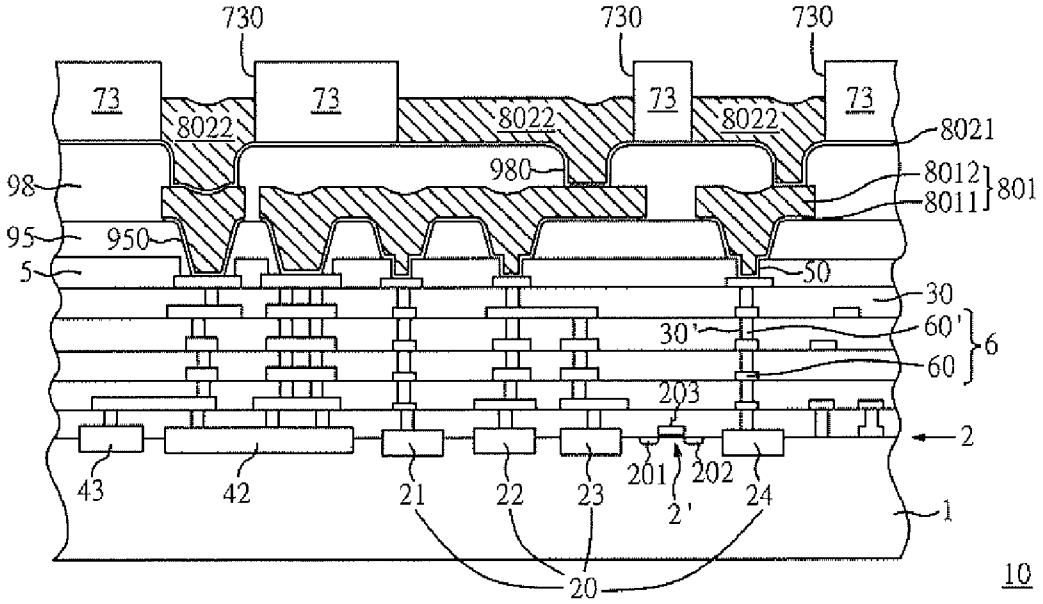


Fig. 18C

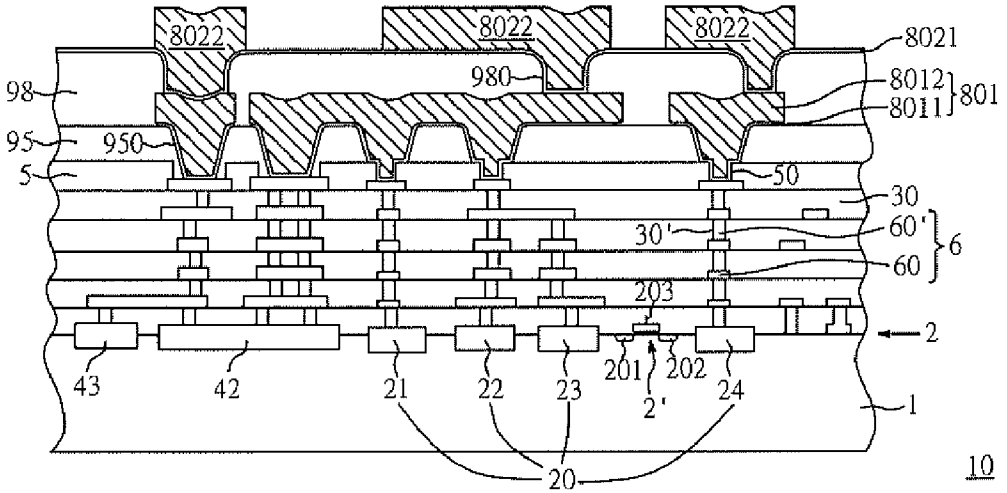


Fig. 18D

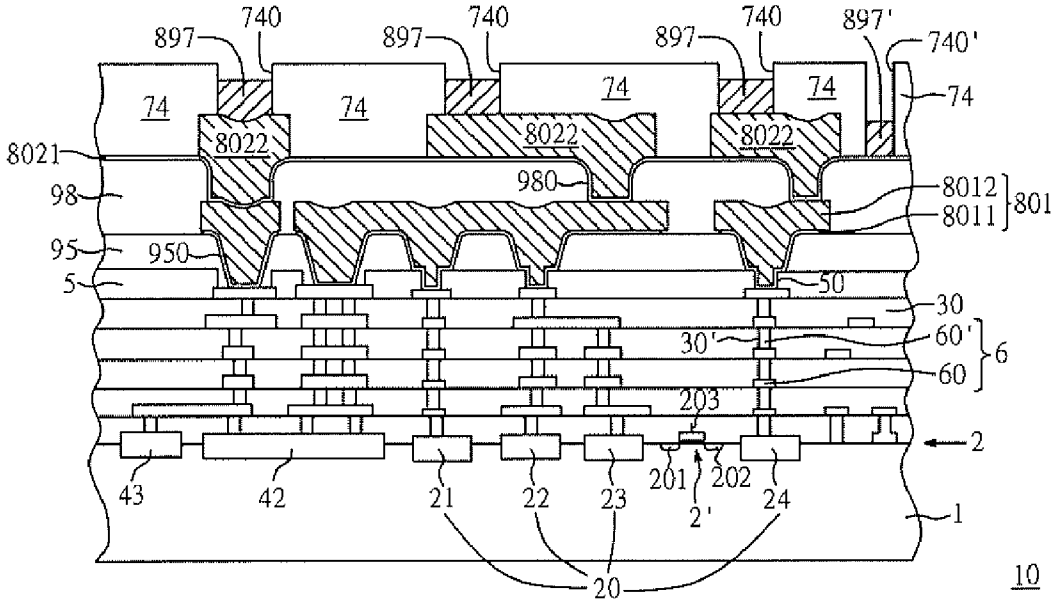


Fig. 18E

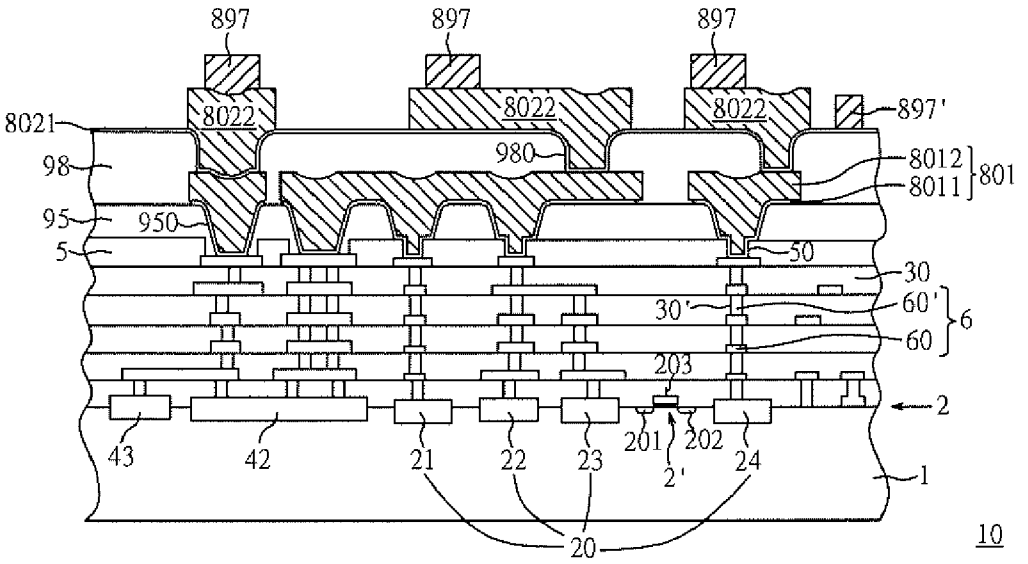


Fig. 18F

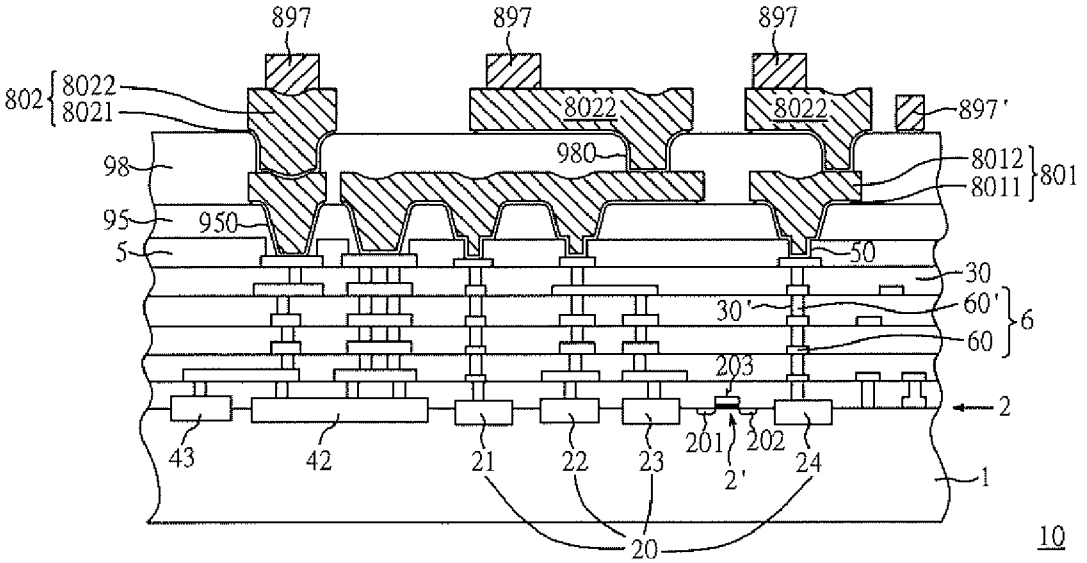


Fig. 18G

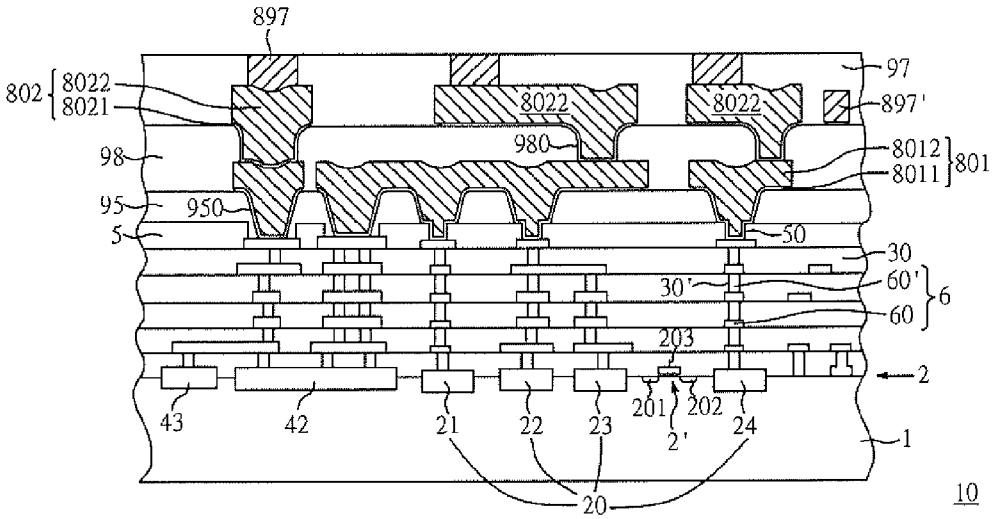


Fig. 18H

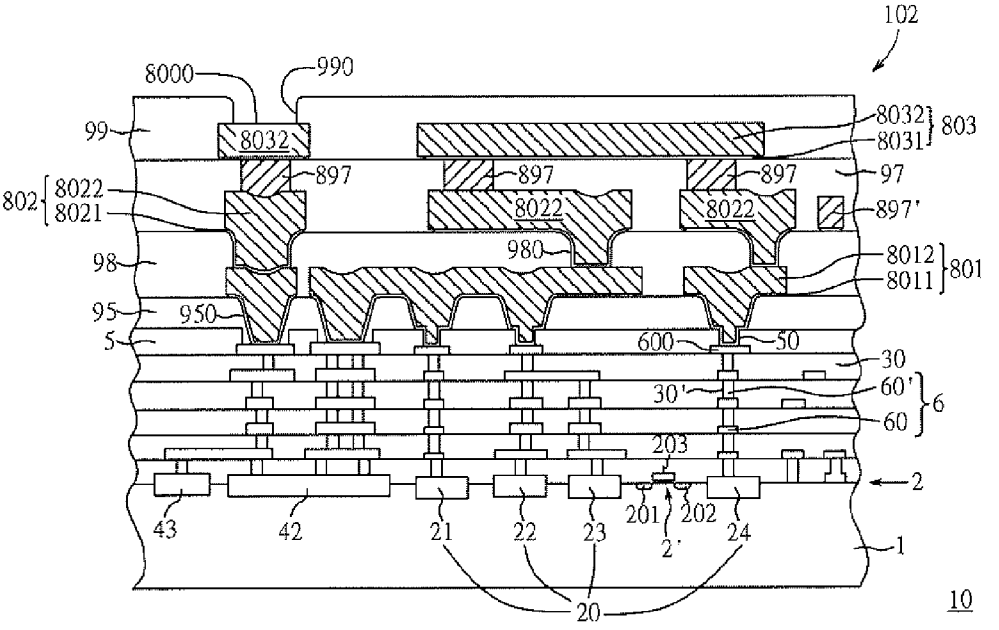


Fig. 18I

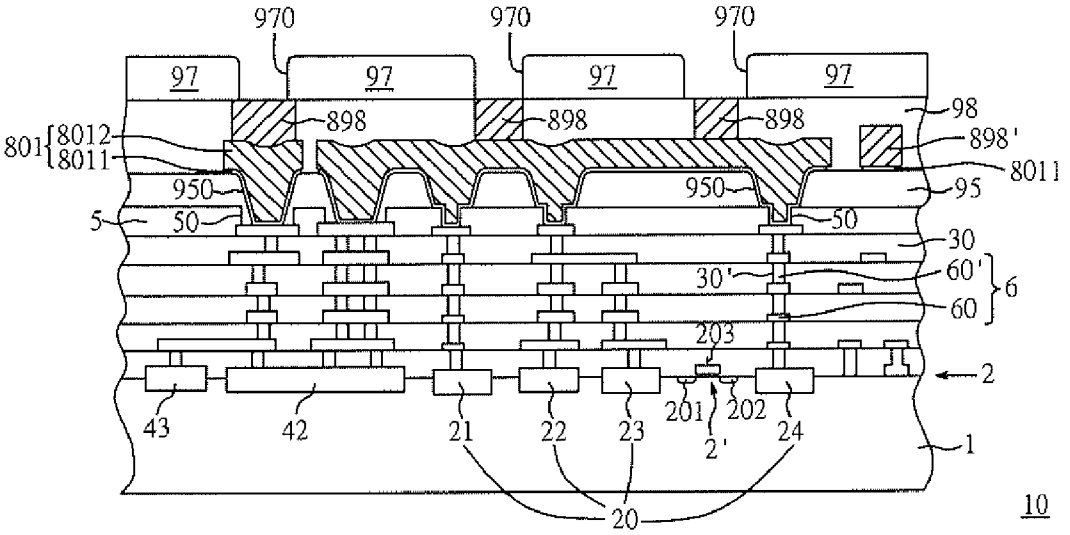


Fig. 19A

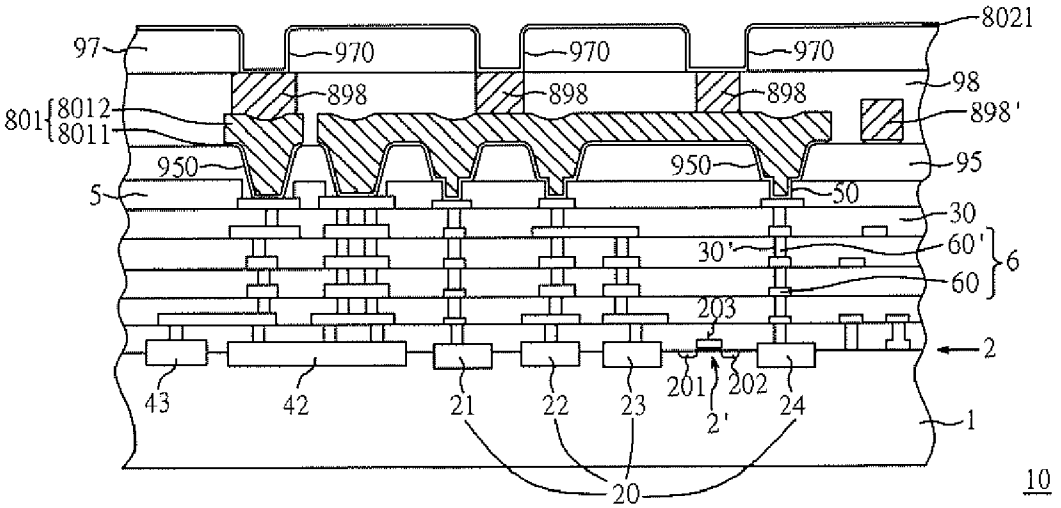


Fig. 19B

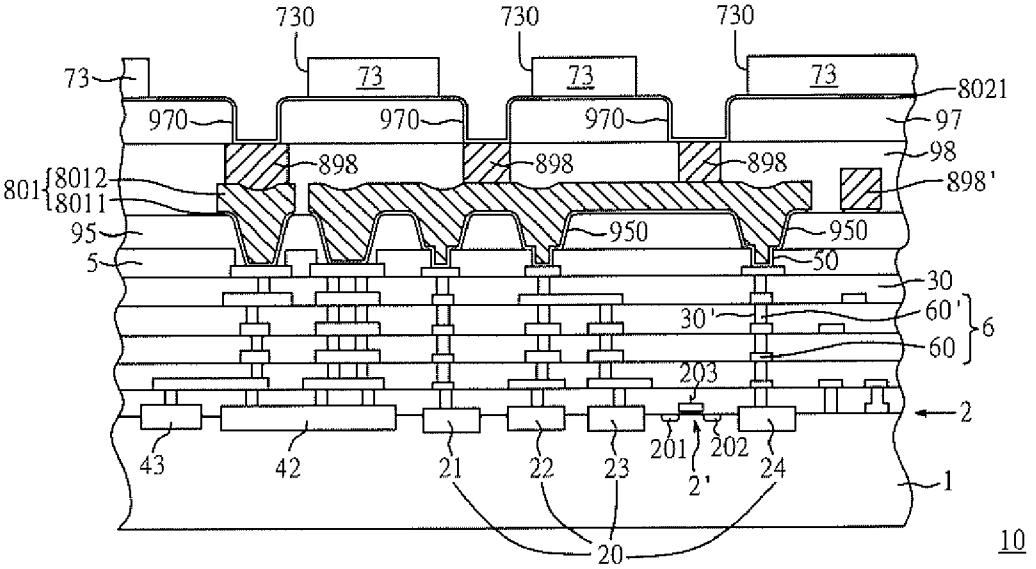


Fig. 19C

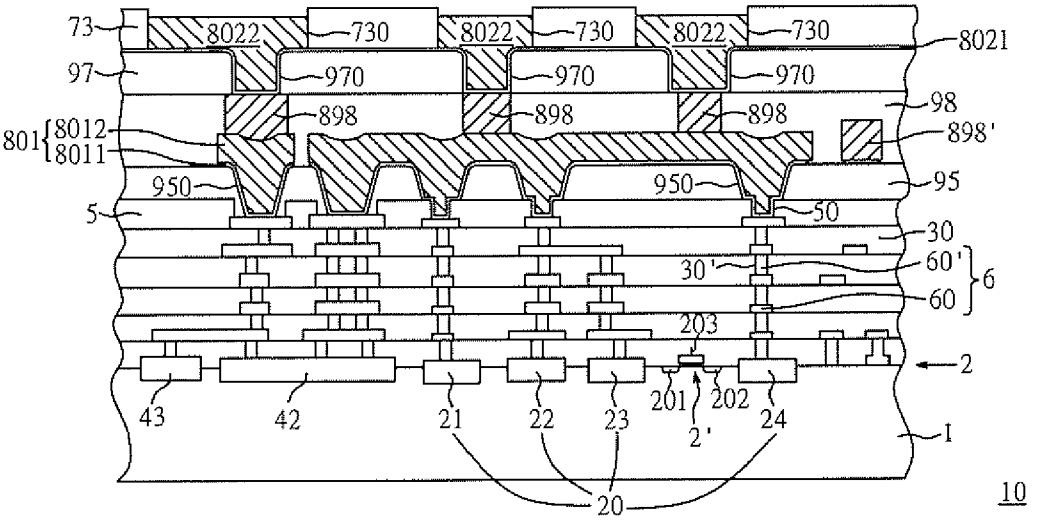


Fig. 19D

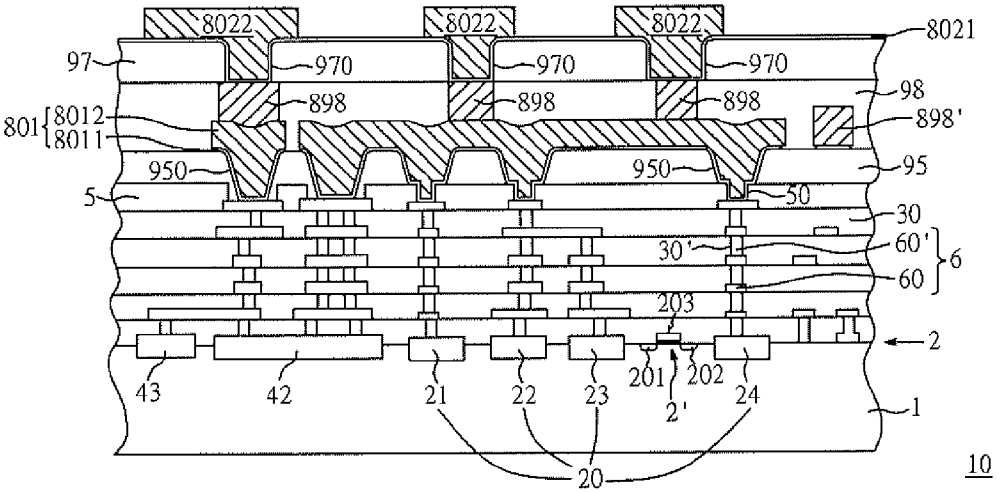


Fig. 19E

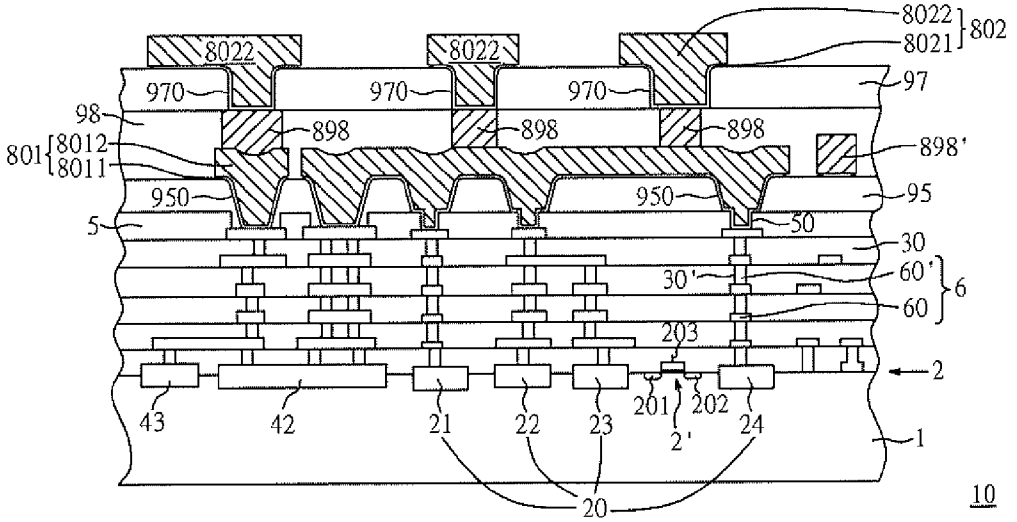


Fig. 19F

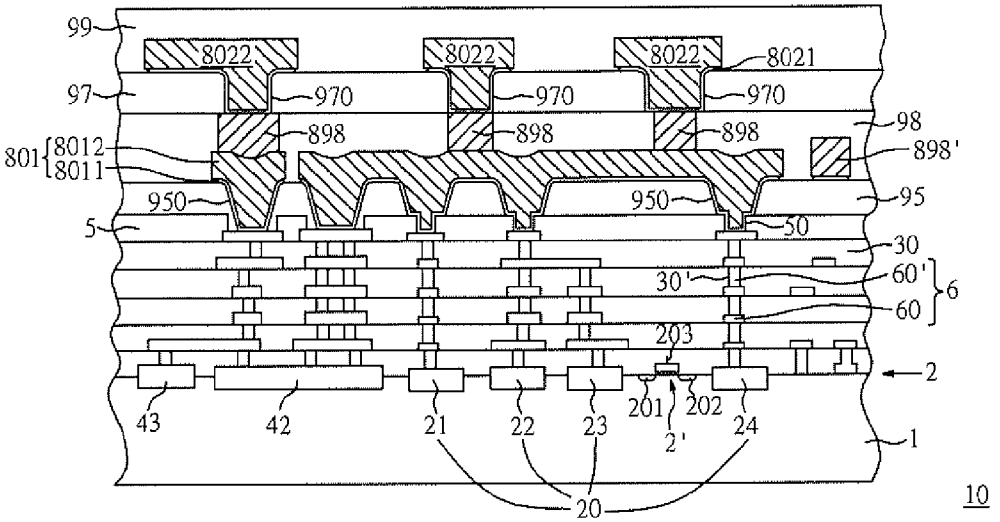


Fig. 19G

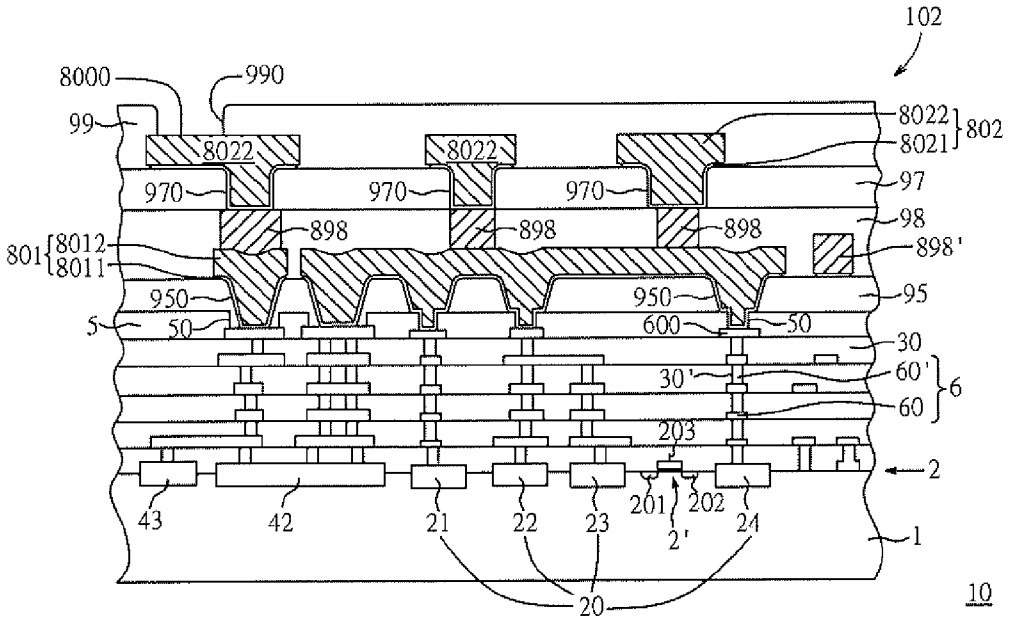


Fig. 19H

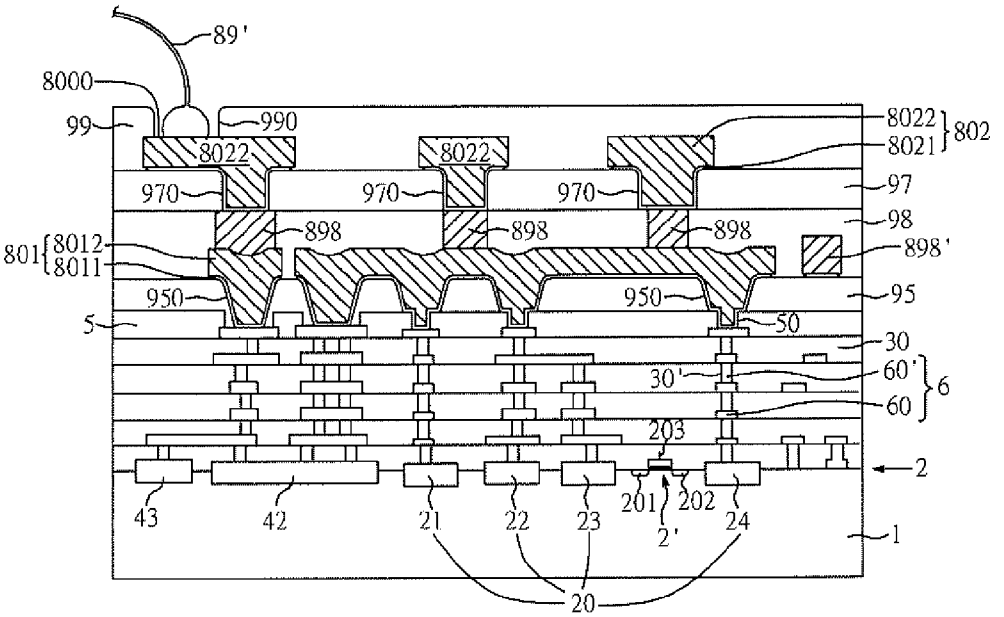


Fig. 19I

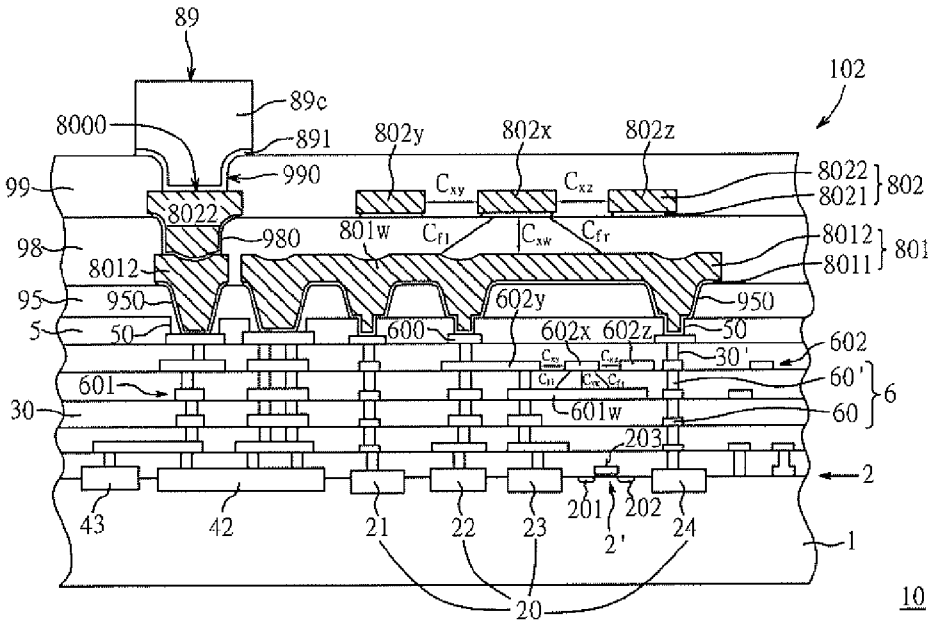


Fig. 20

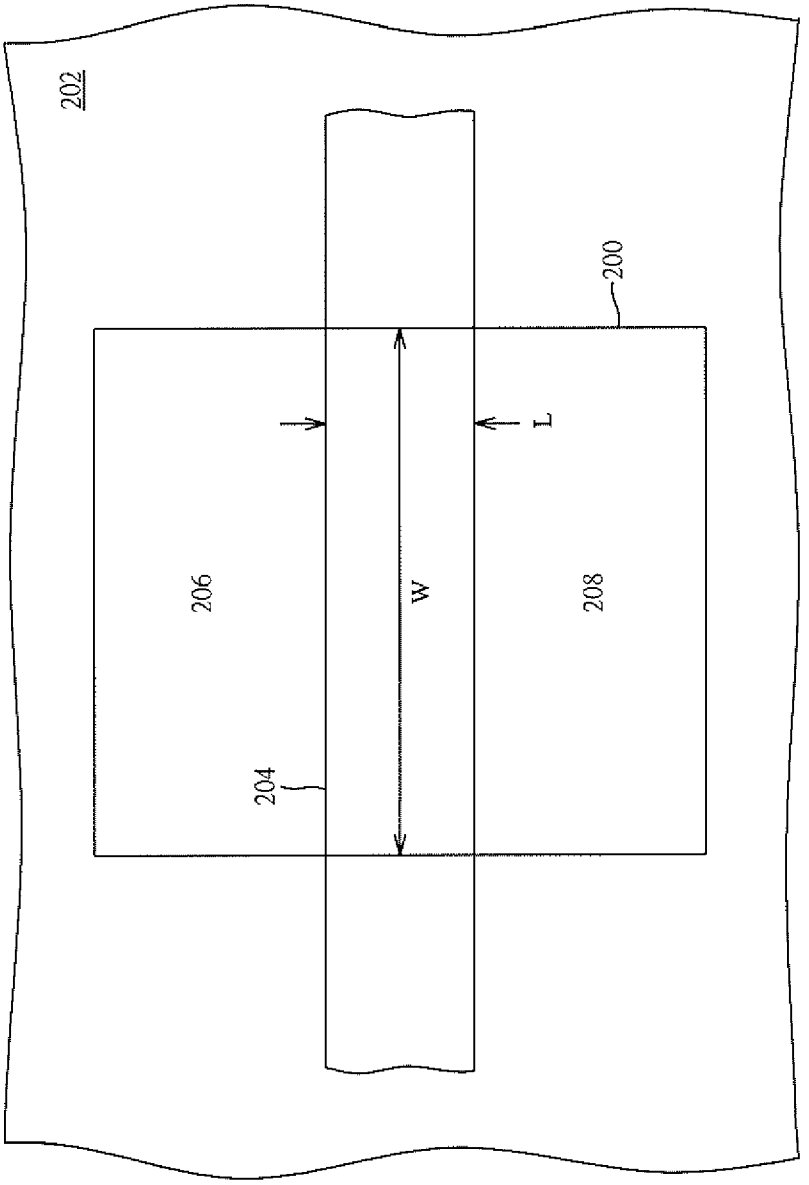


Fig. 21

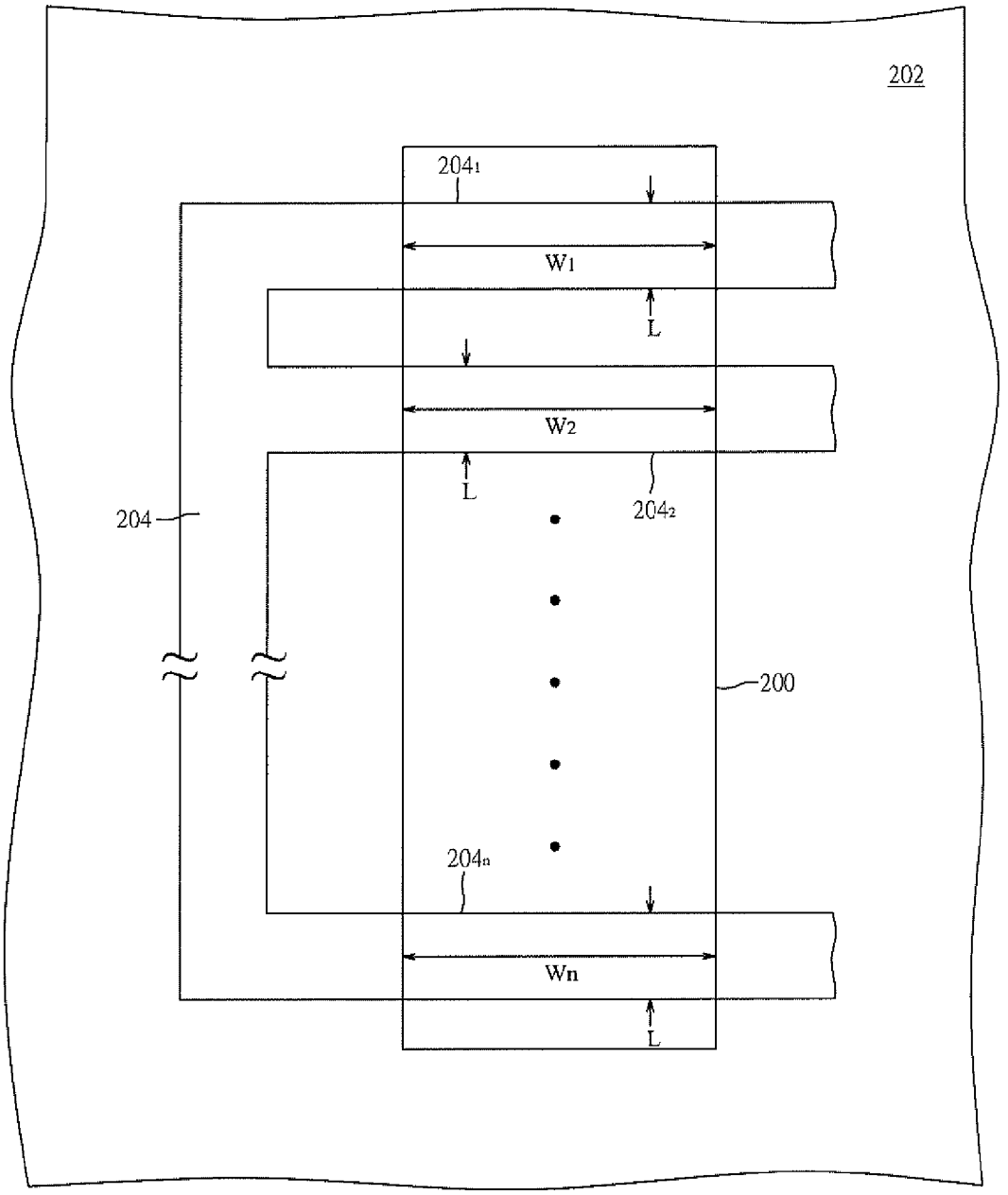


Fig. 22

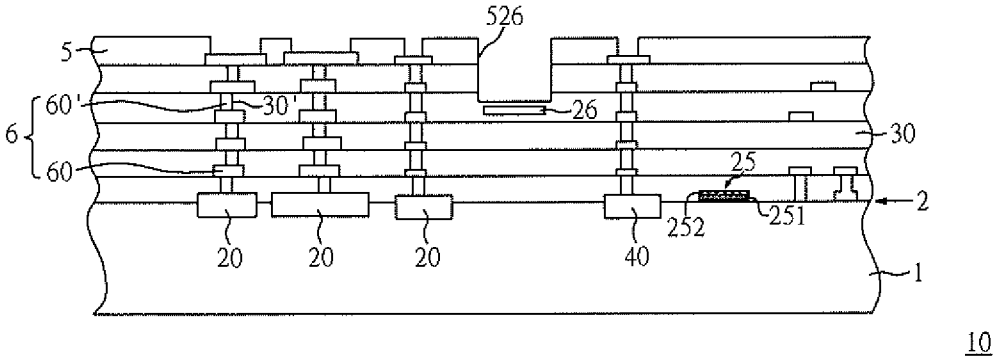


Fig. 23A

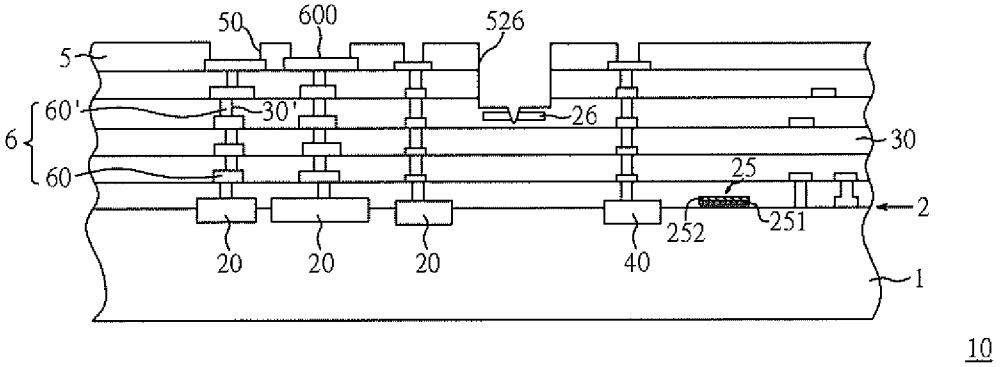


Fig. 23B

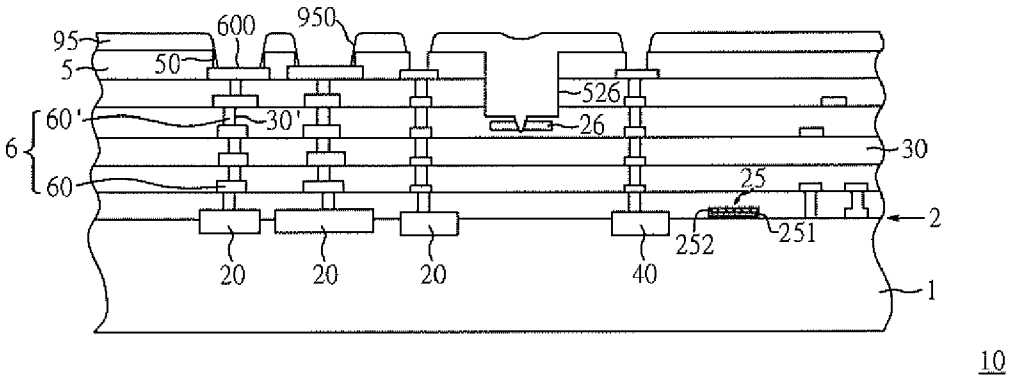


Fig. 23C

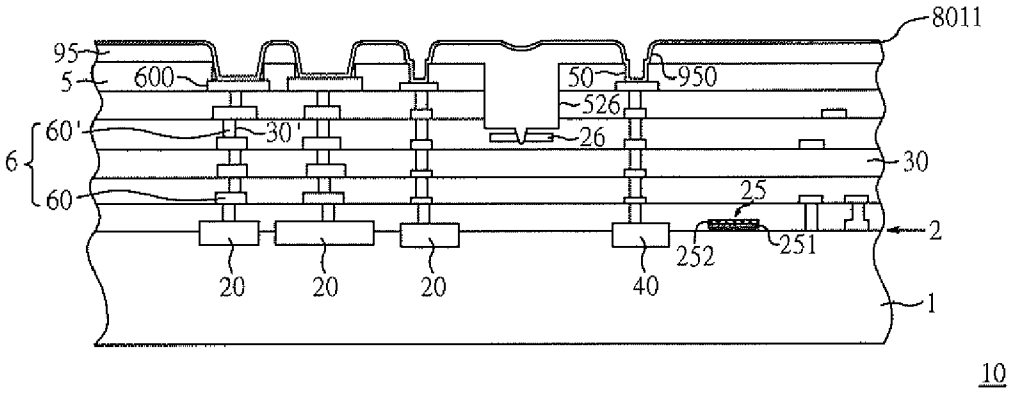


Fig. 23D

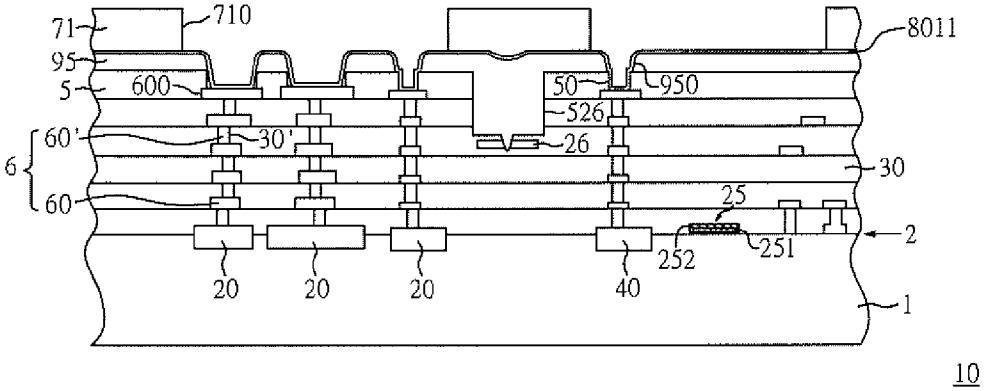


Fig. 23E

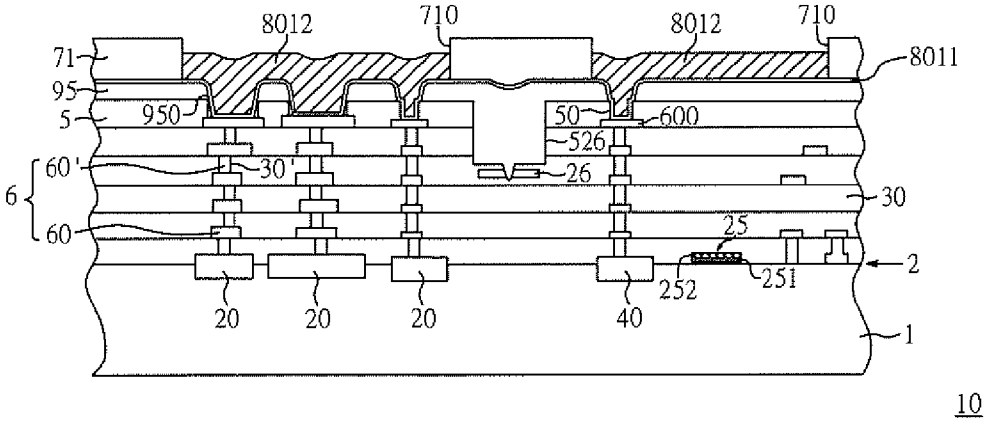


Fig. 23F

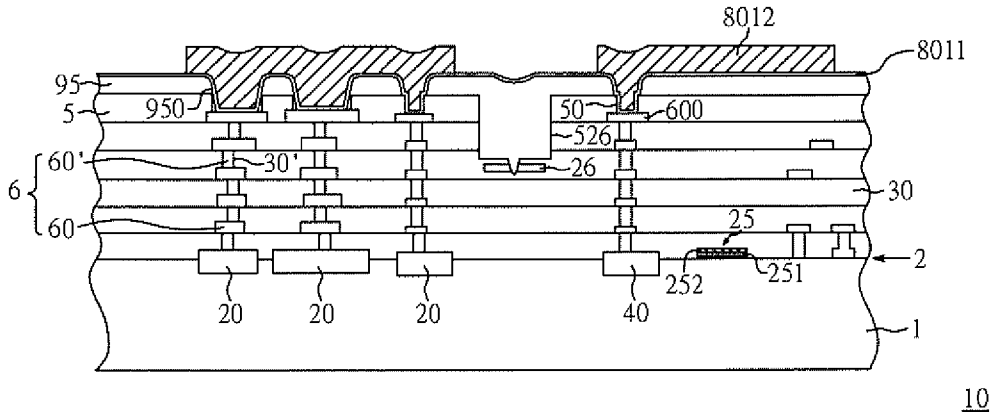


Fig. 23G

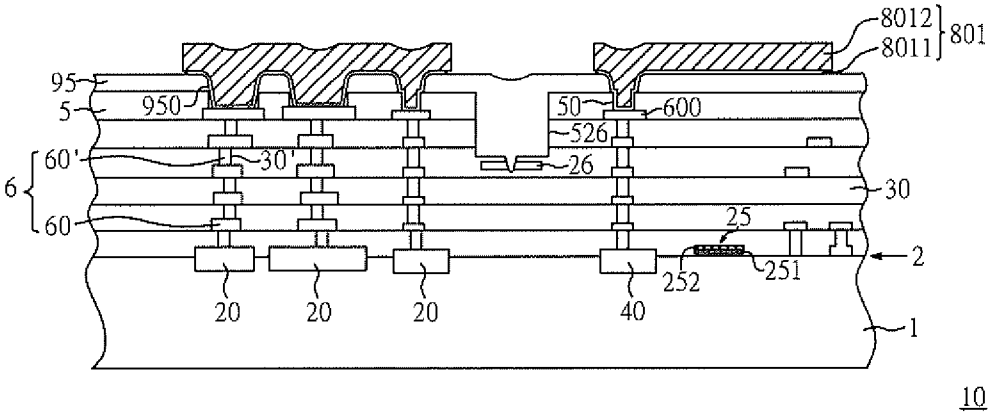


Fig. 23H

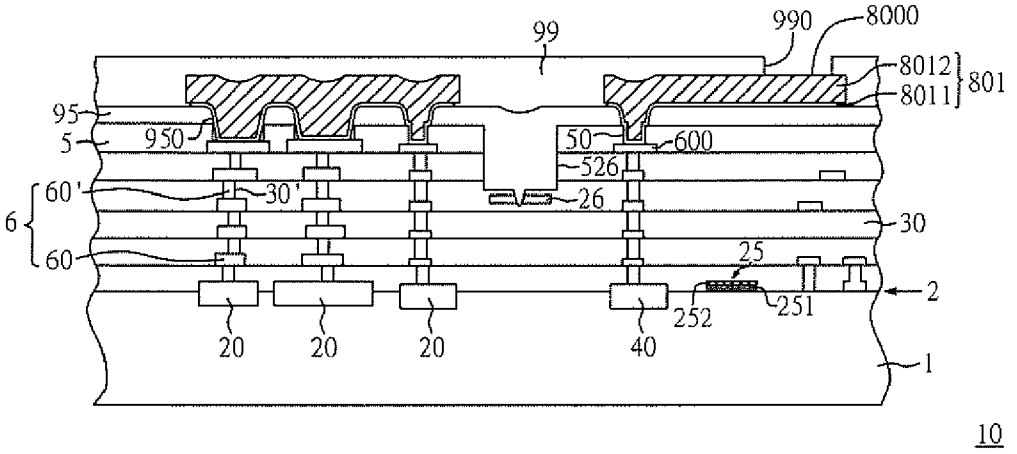


Fig. 23I

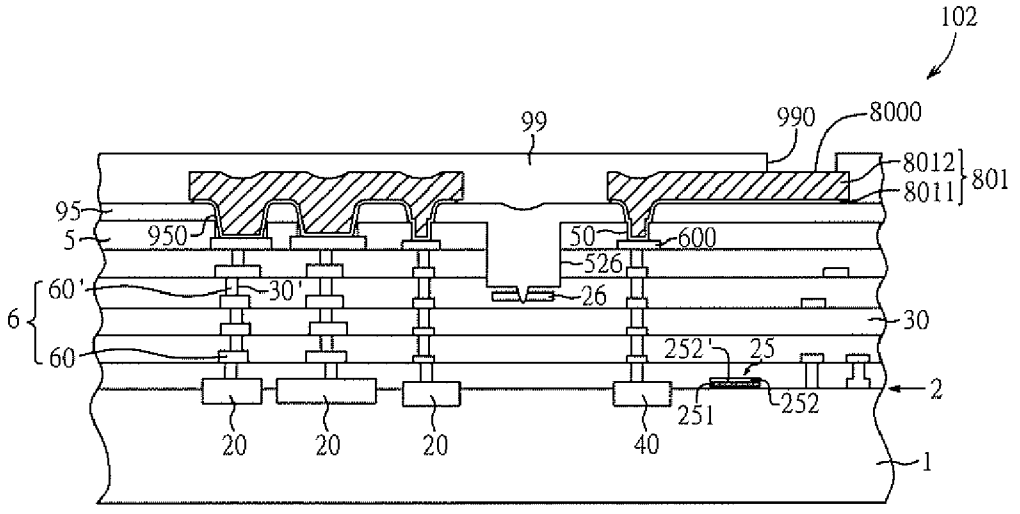


Fig. 23J

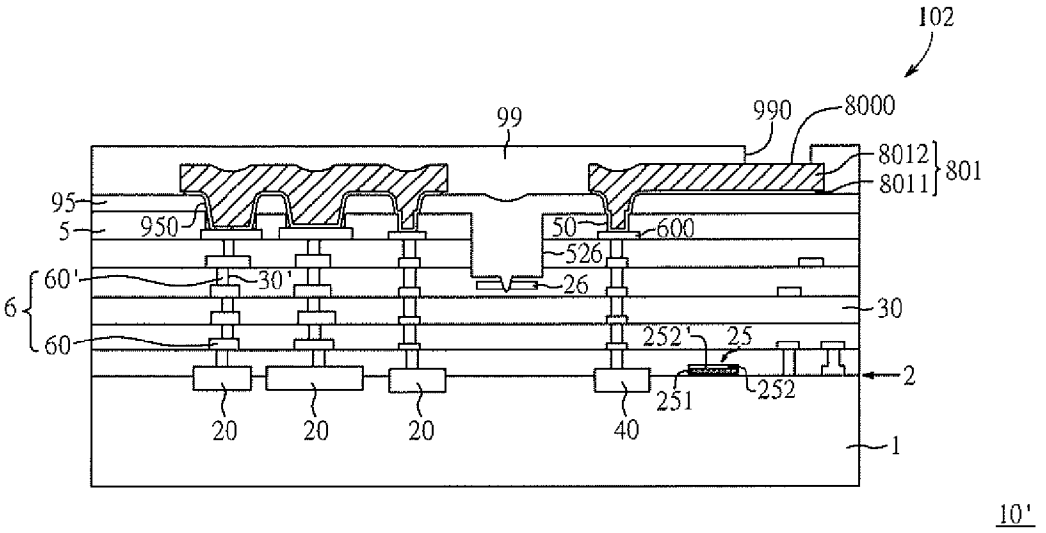


Fig. 23K

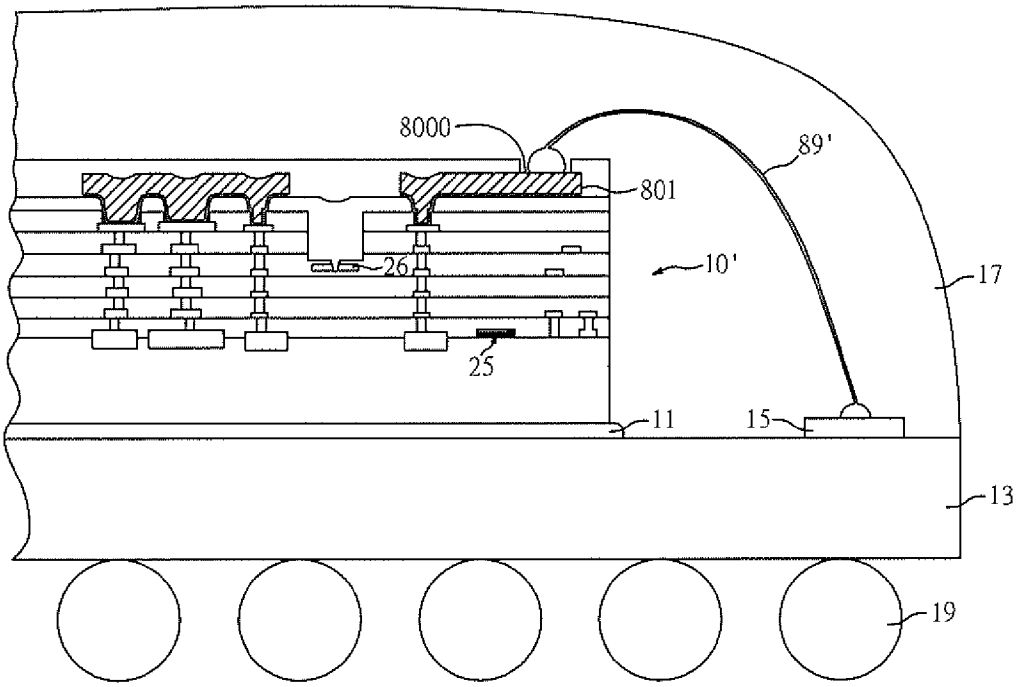


Fig. 23L

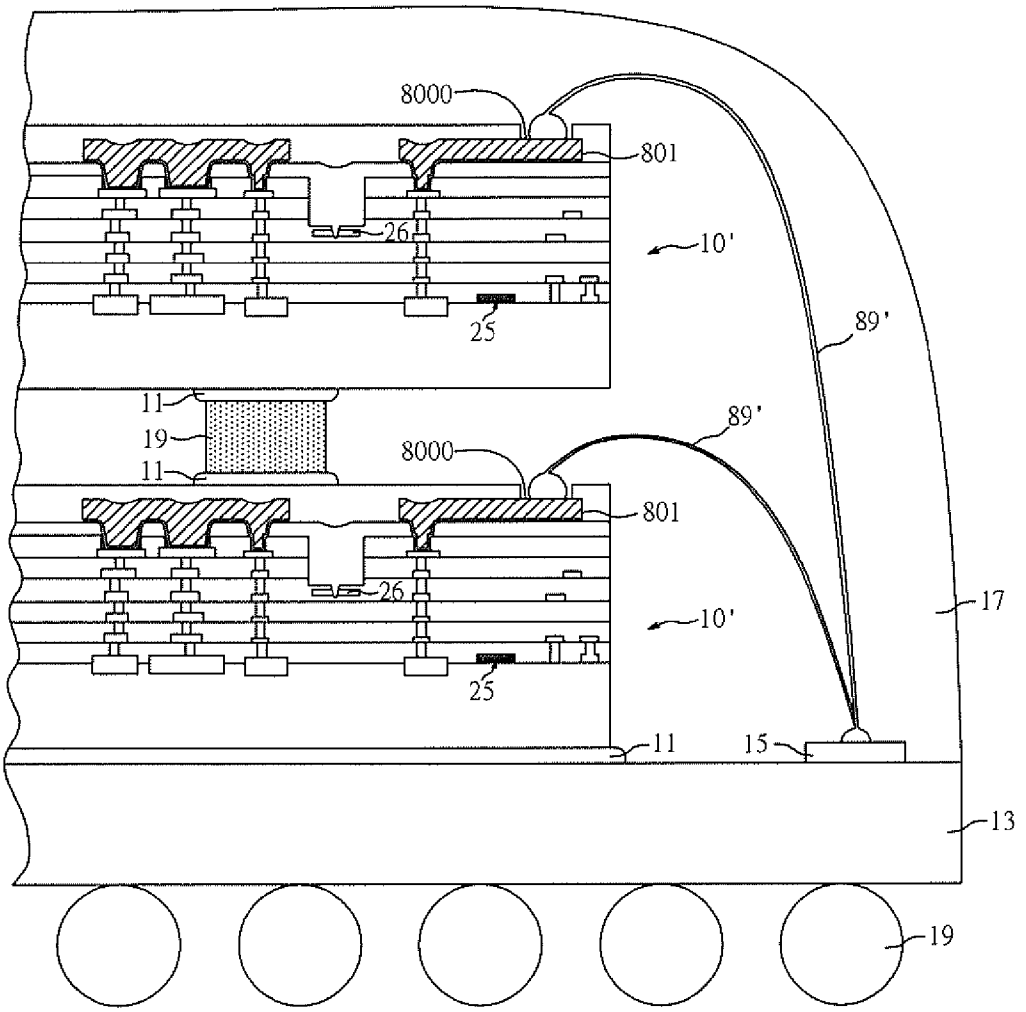


Fig. 23M

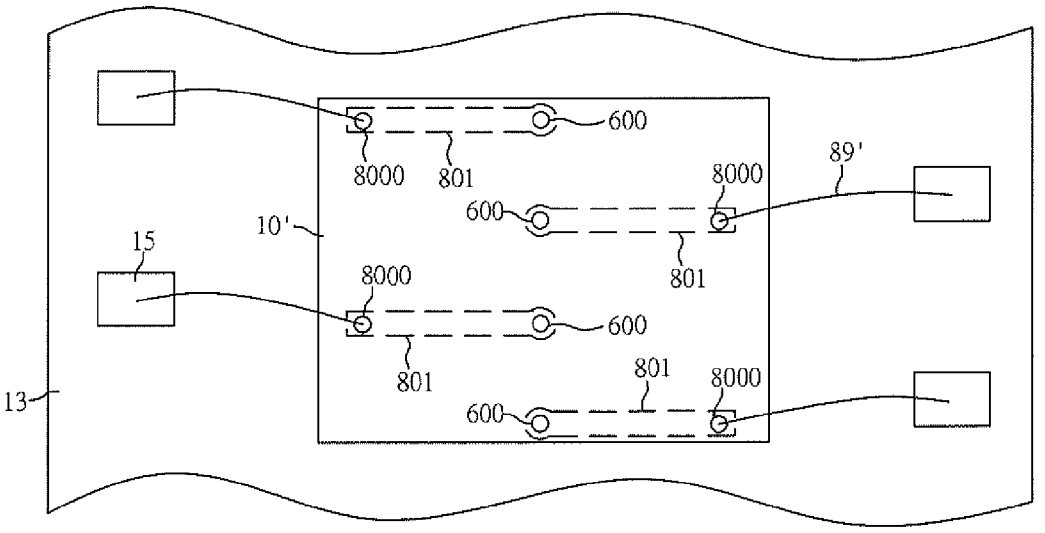


Fig. 23N

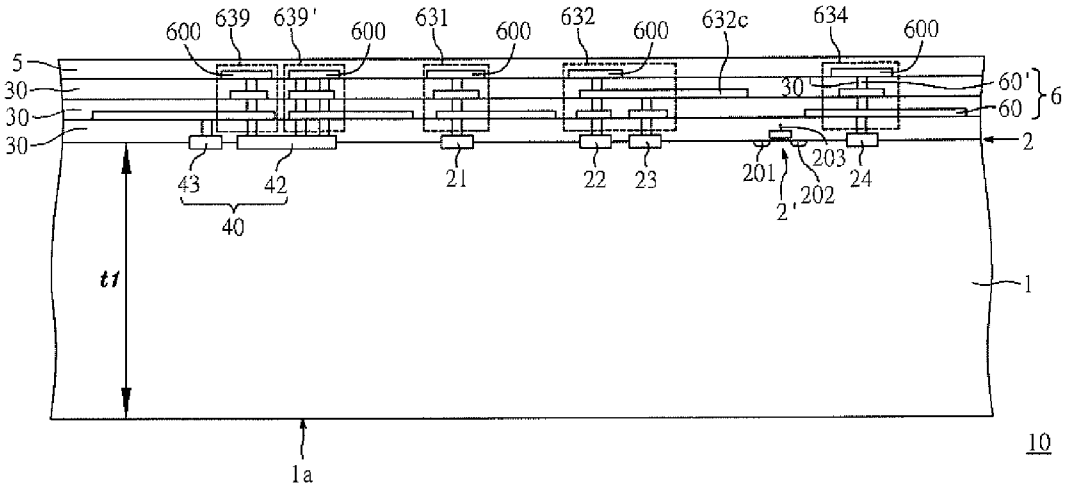


Fig. 24A

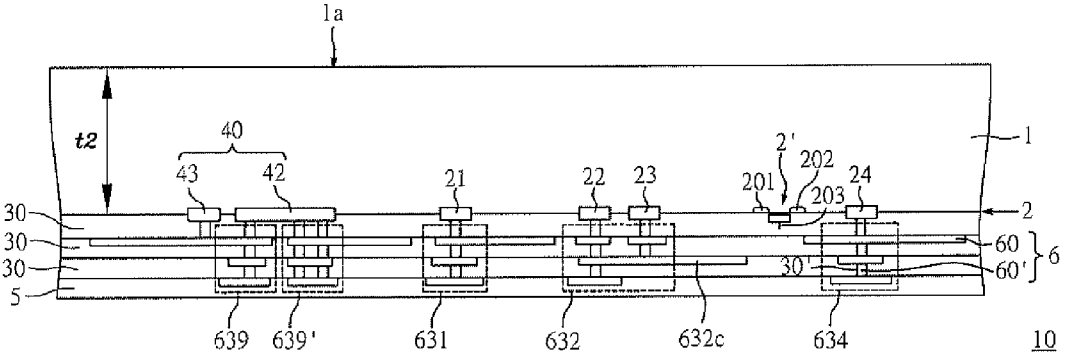


Fig. 24B

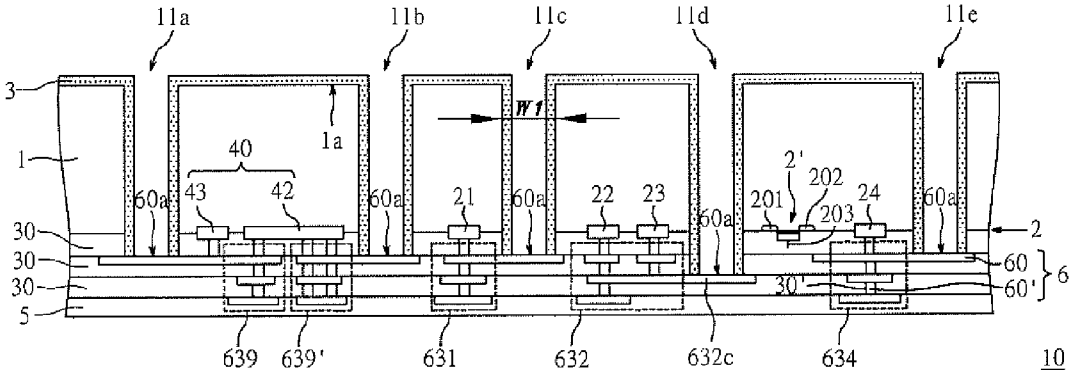


Fig. 24C

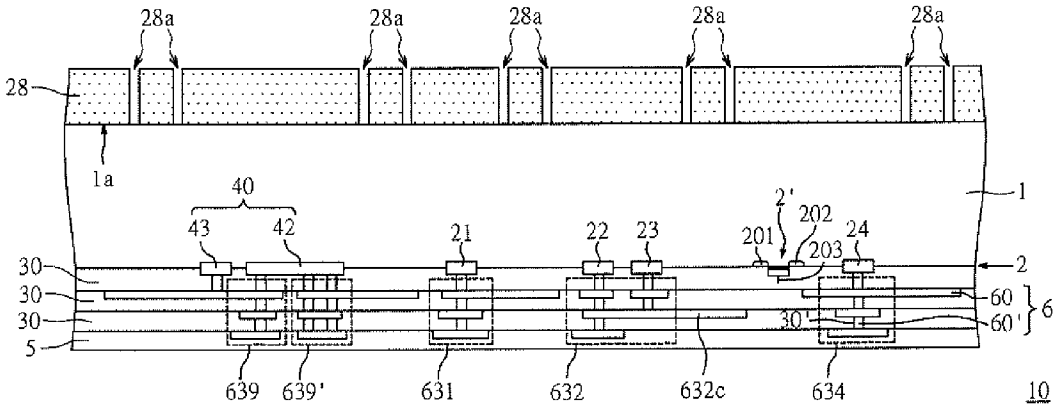


Fig. 24D

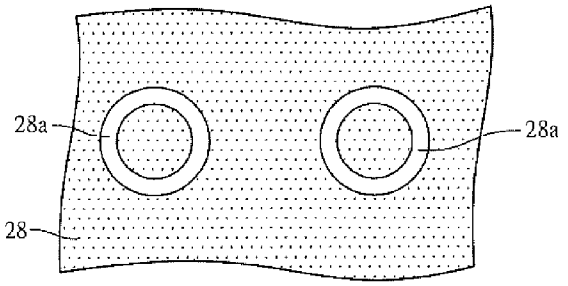


Fig. 24E

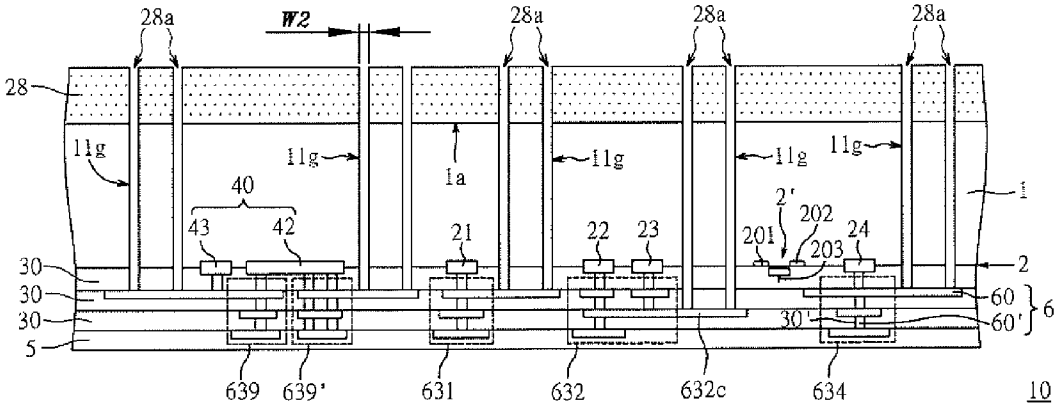


Fig. 24F

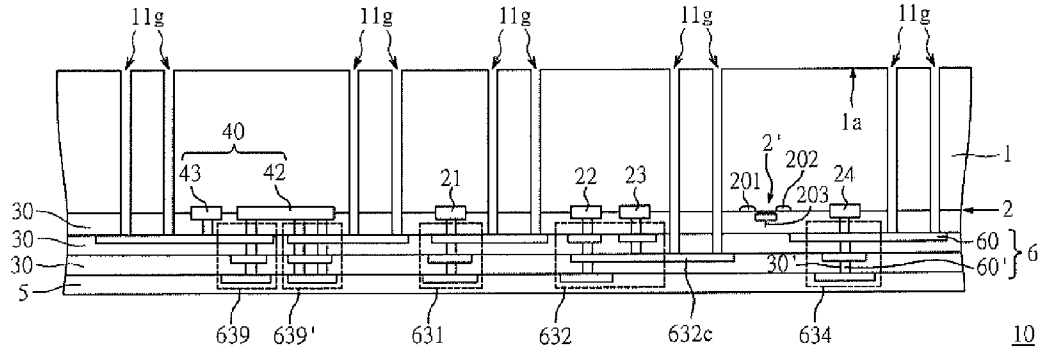


Fig. 24G

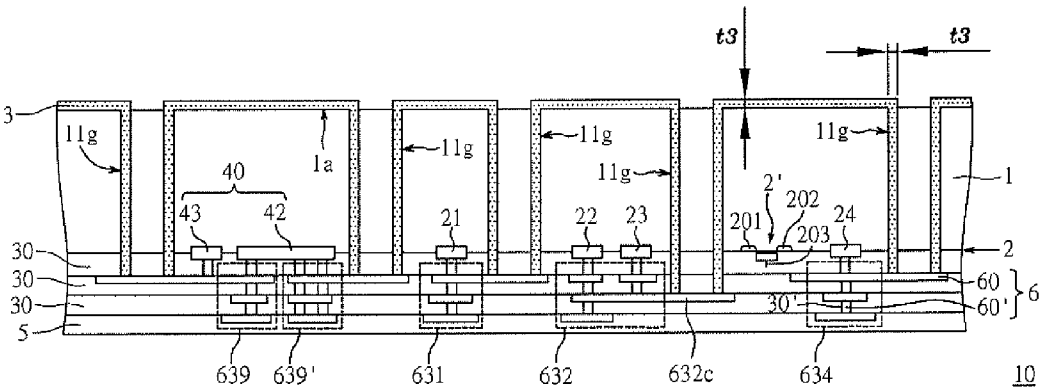


Fig. 24H

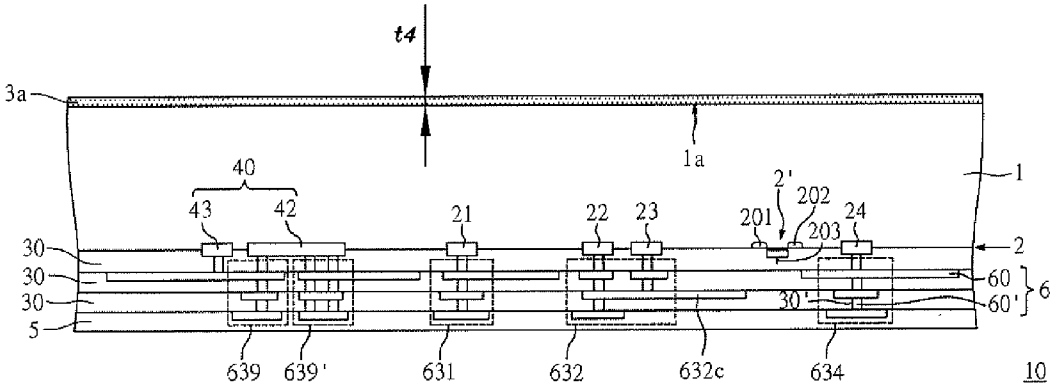


Fig. 24I

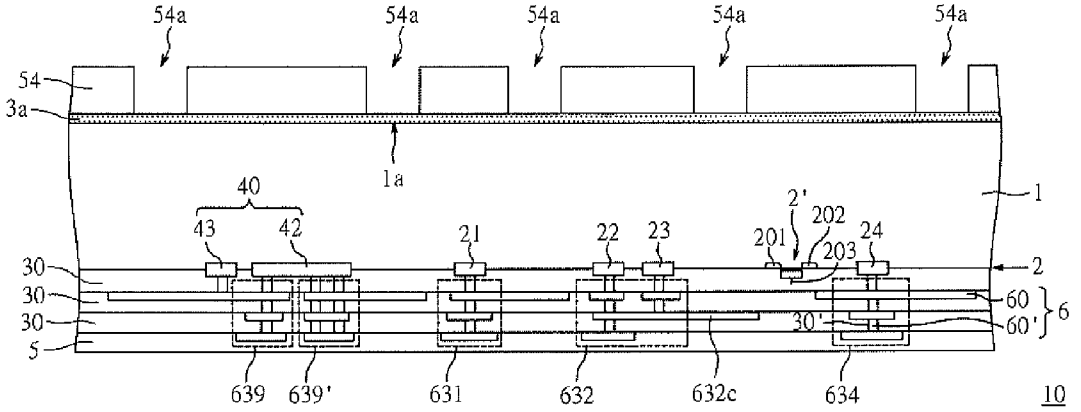


Fig. 24J

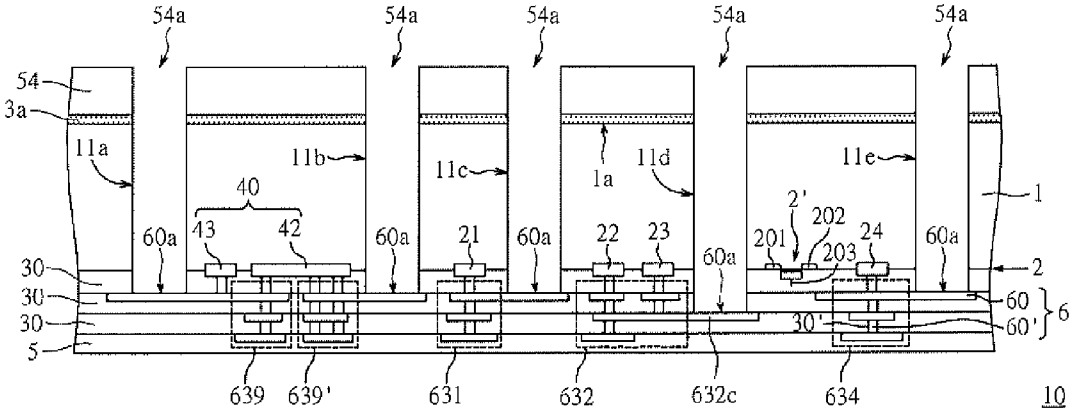


Fig. 24K

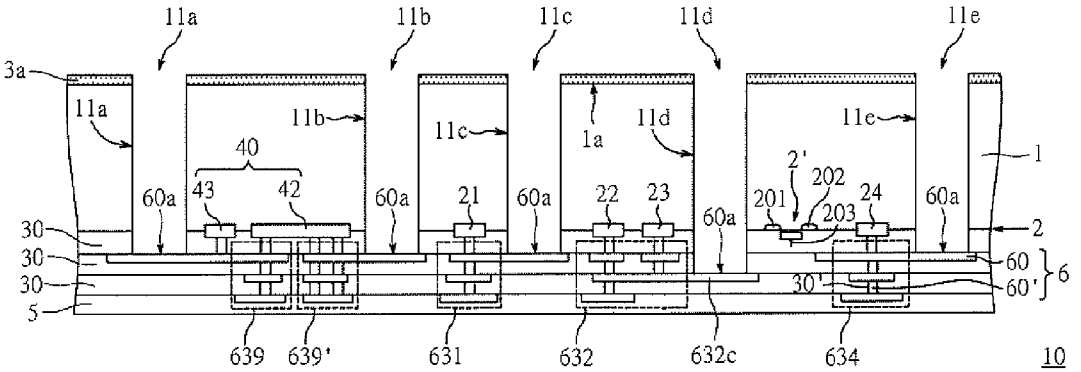


Fig. 24L

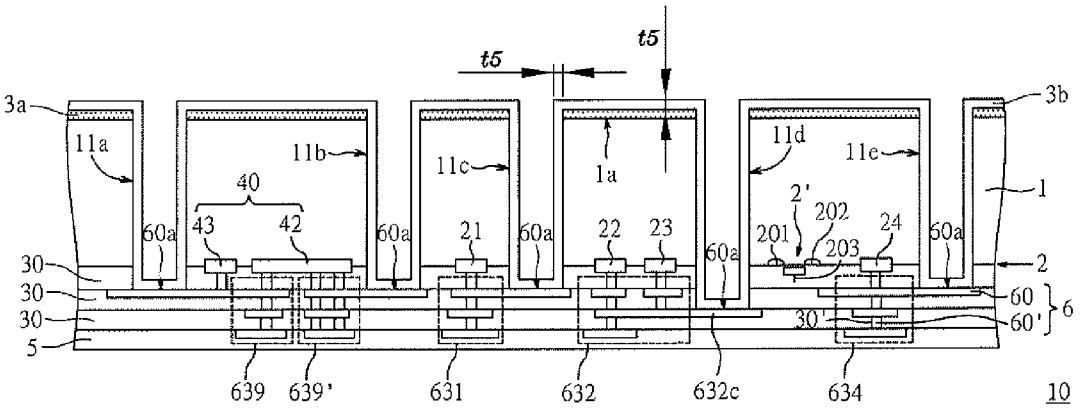


Fig. 24M

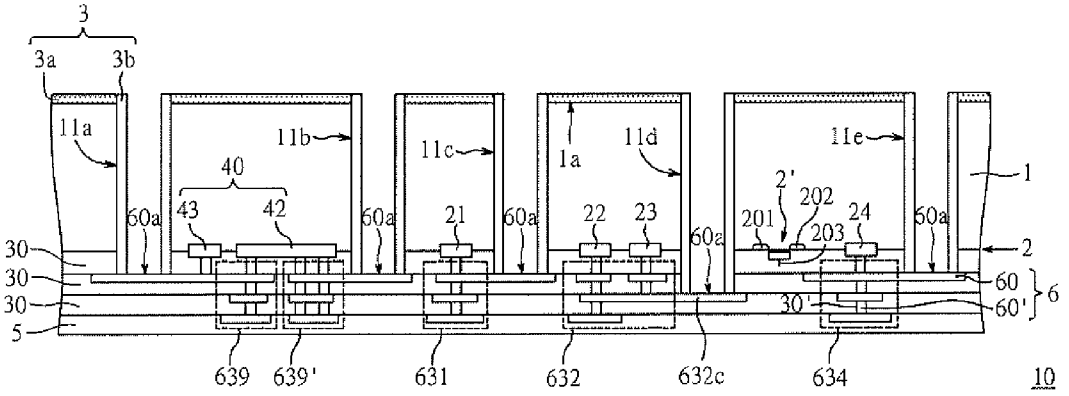


Fig. 24N

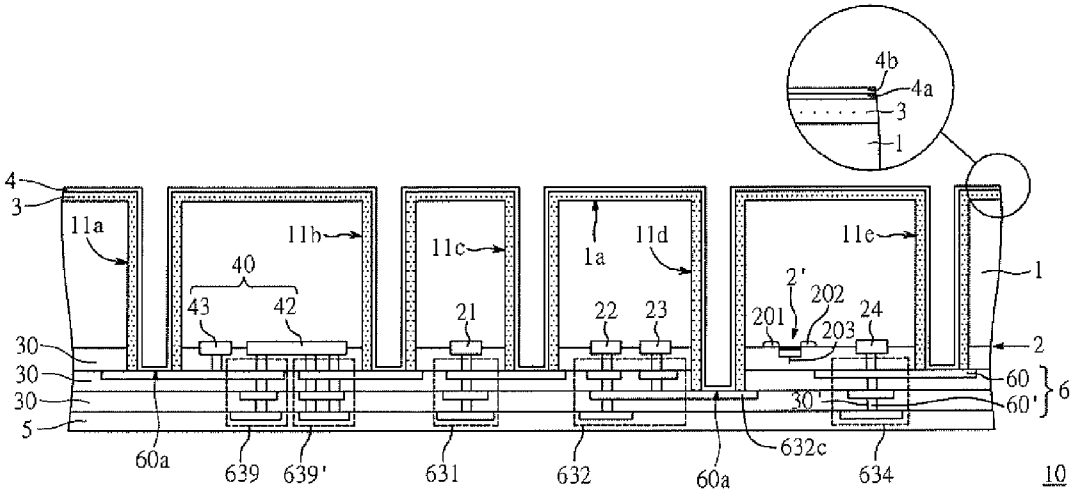


Fig. 25A

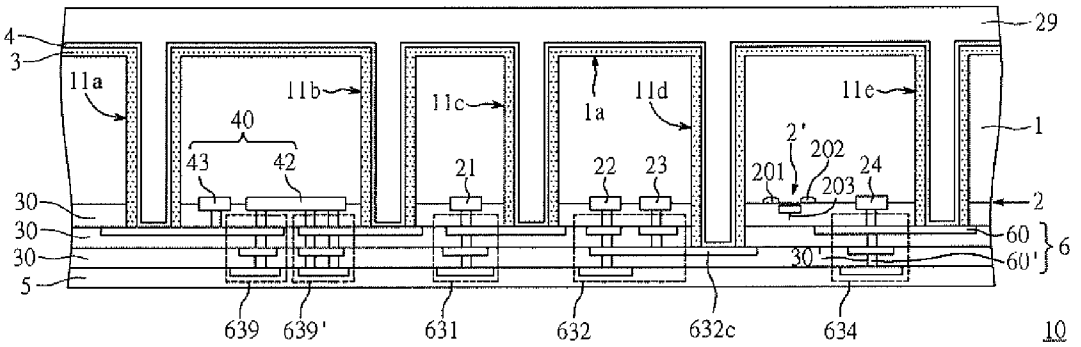


Fig. 25B

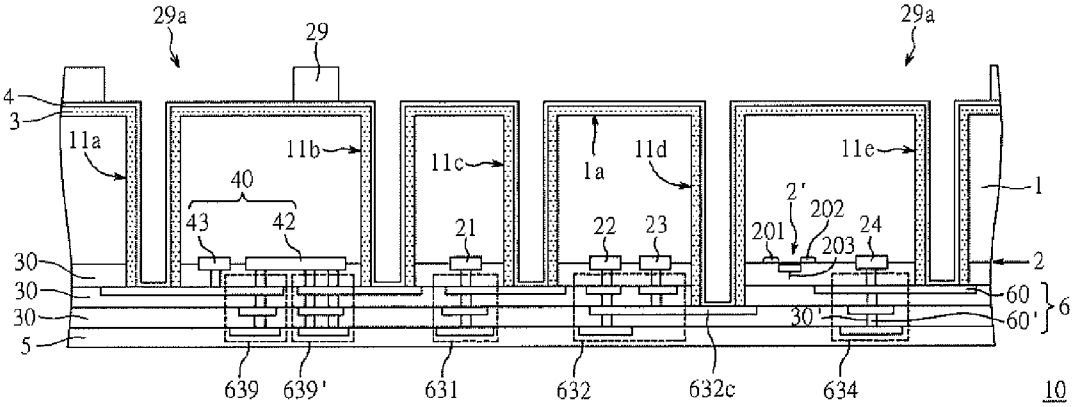


Fig. 25C

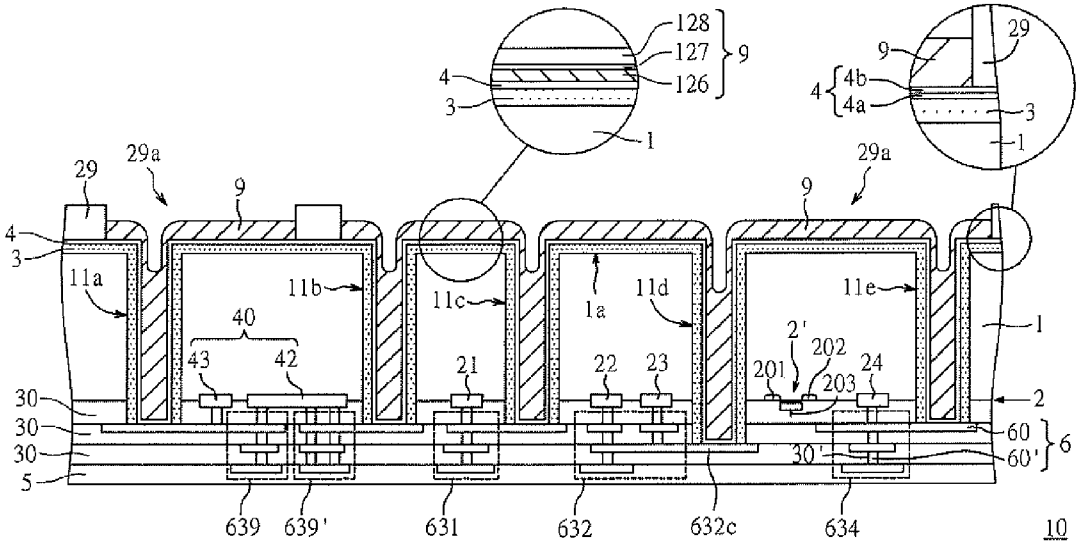


Fig. 25D

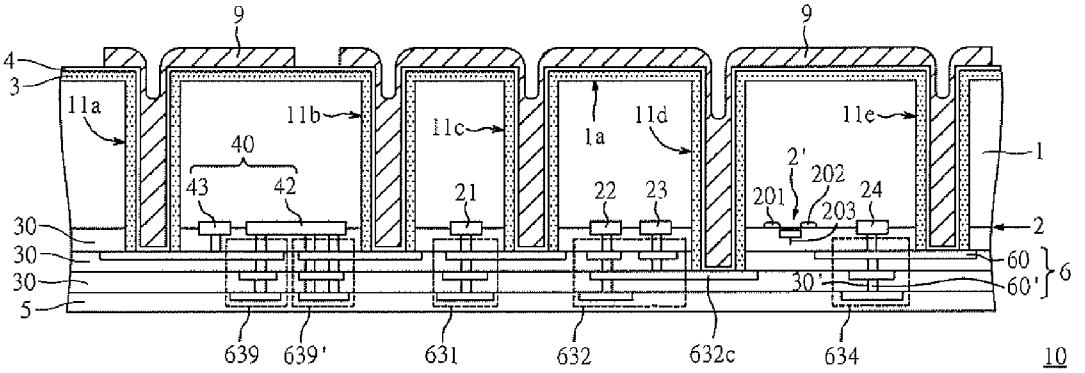


Fig. 25E

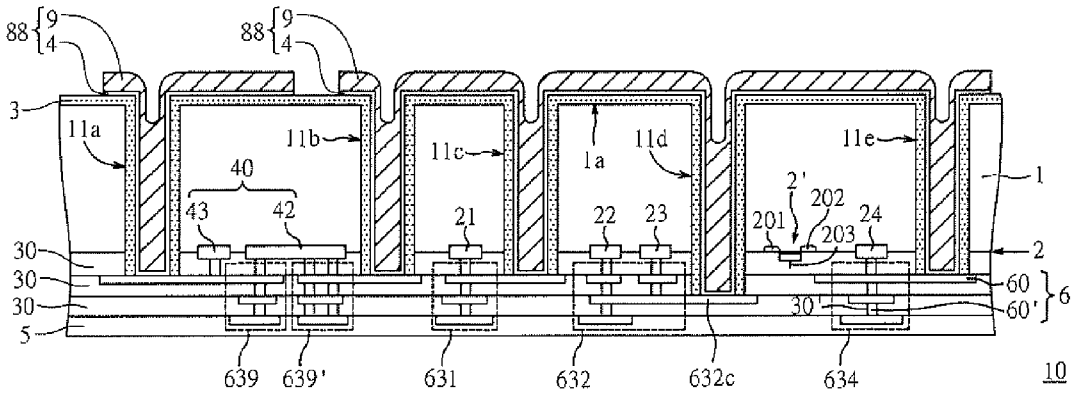


Fig. 25F

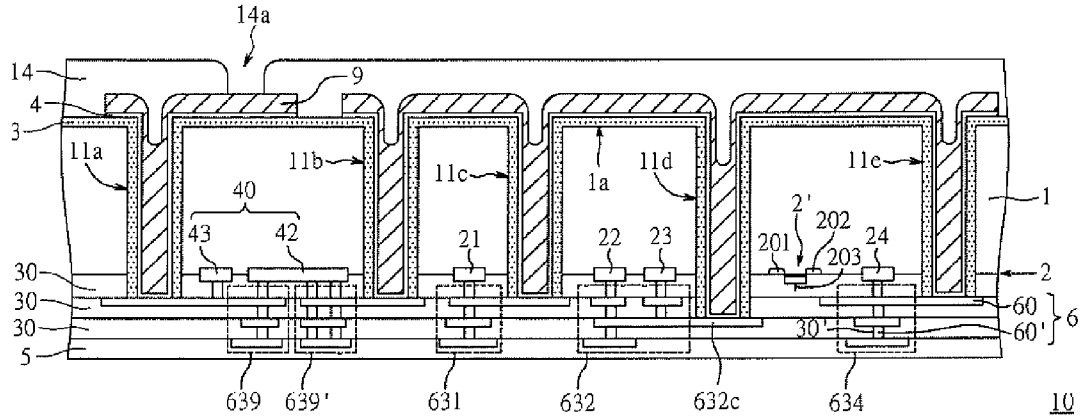


Fig. 25G

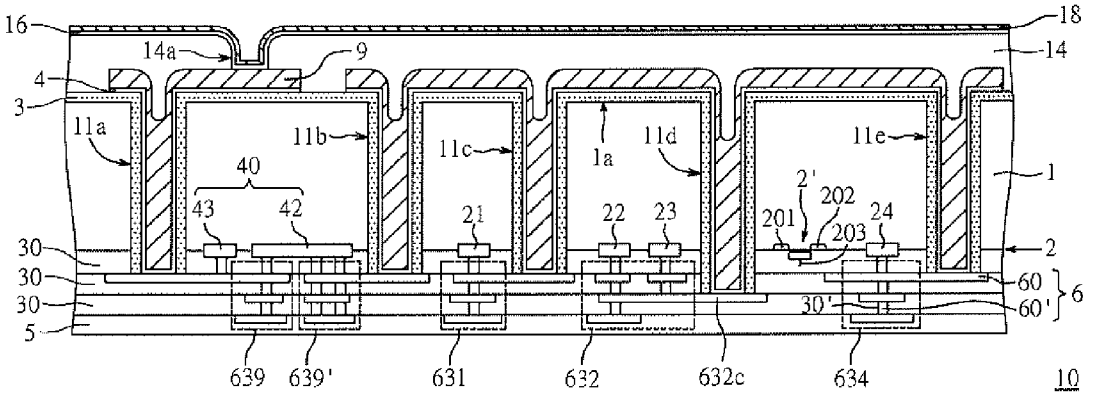


Fig. 25H

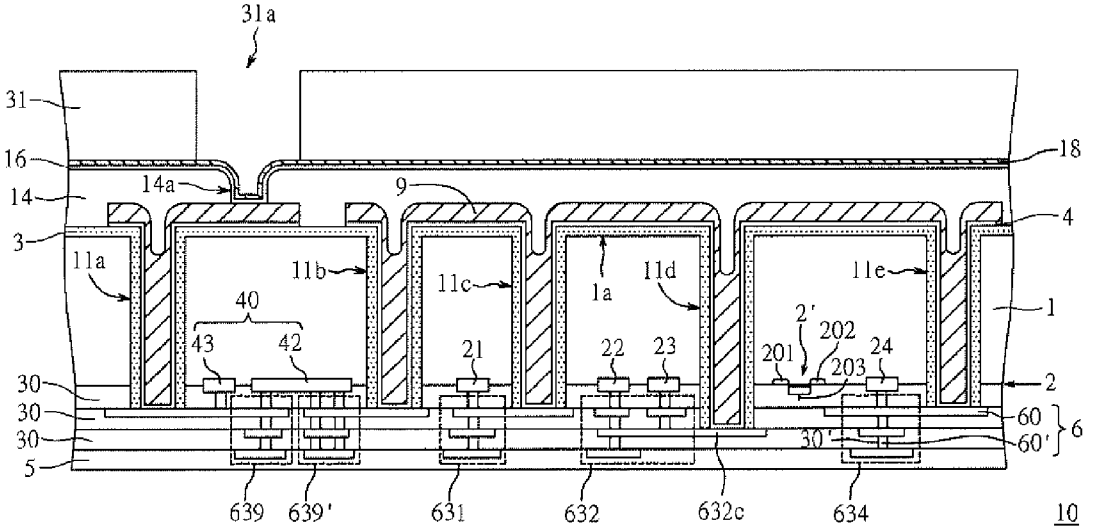


Fig. 25I

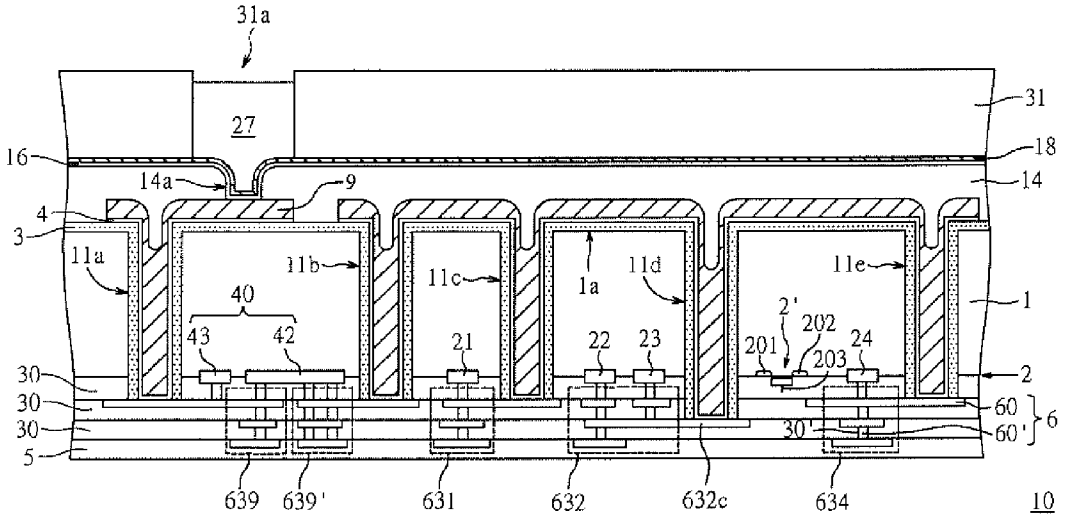


Fig. 25J

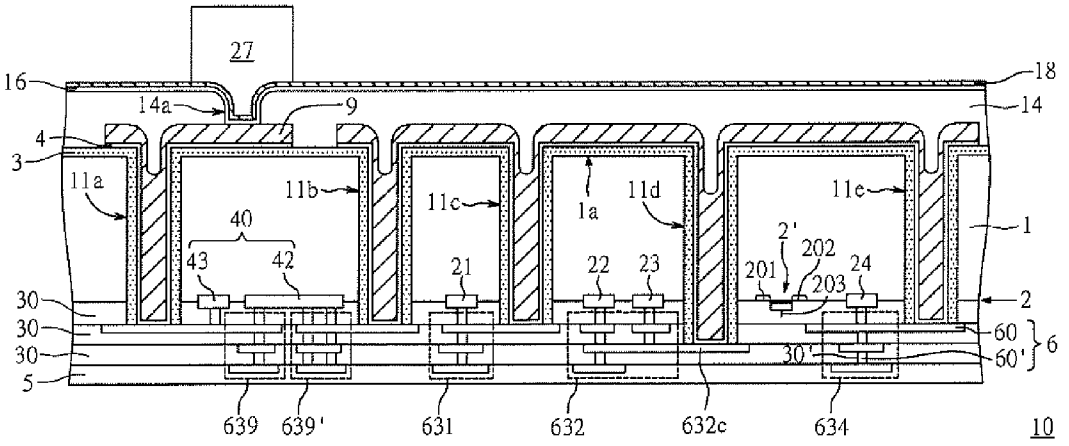


Fig. 25K

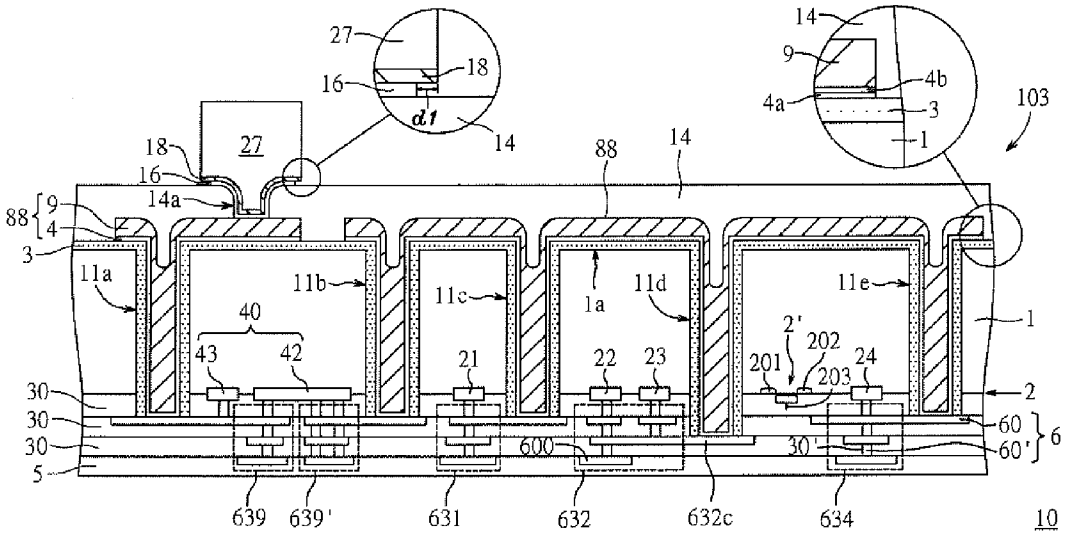


Fig. 25L

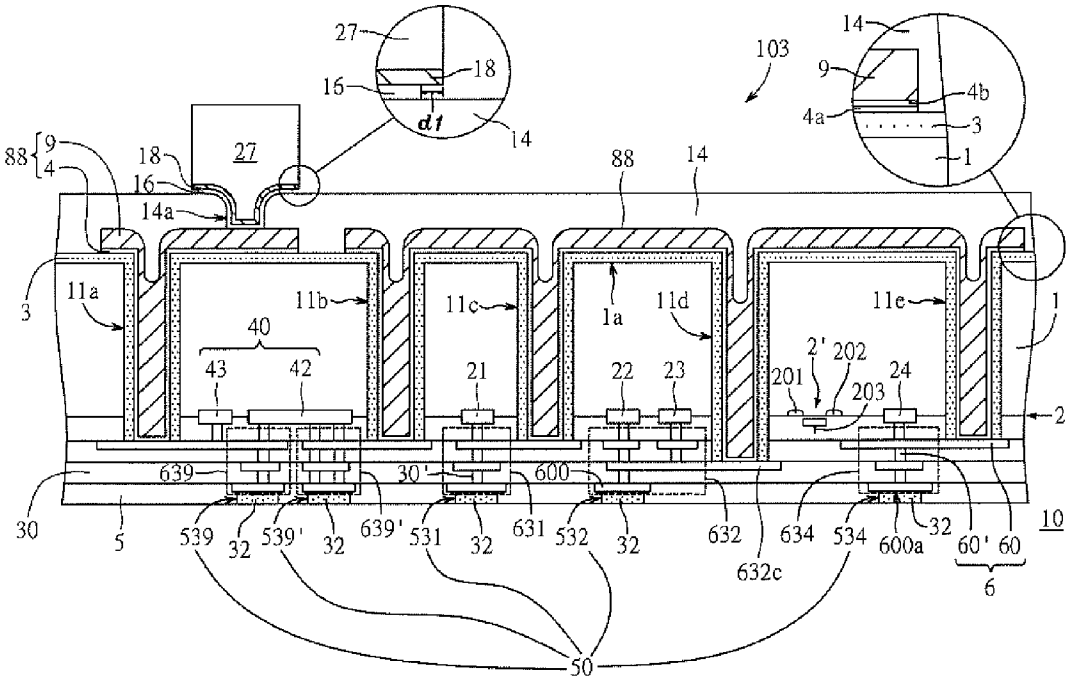


Fig. 25M

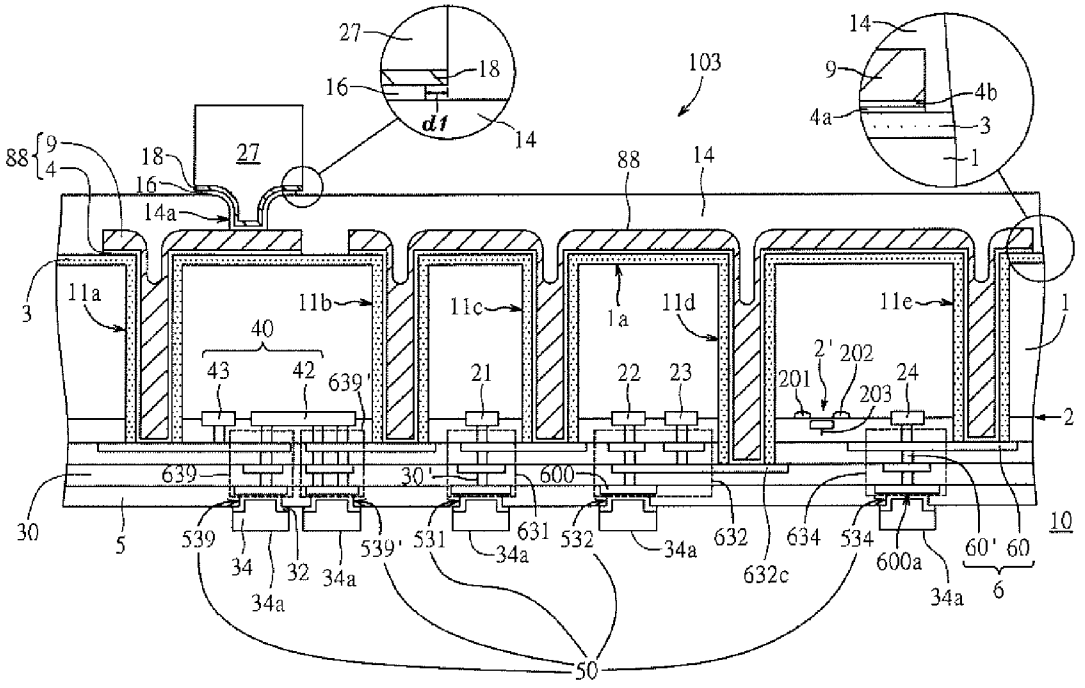


Fig. 25N

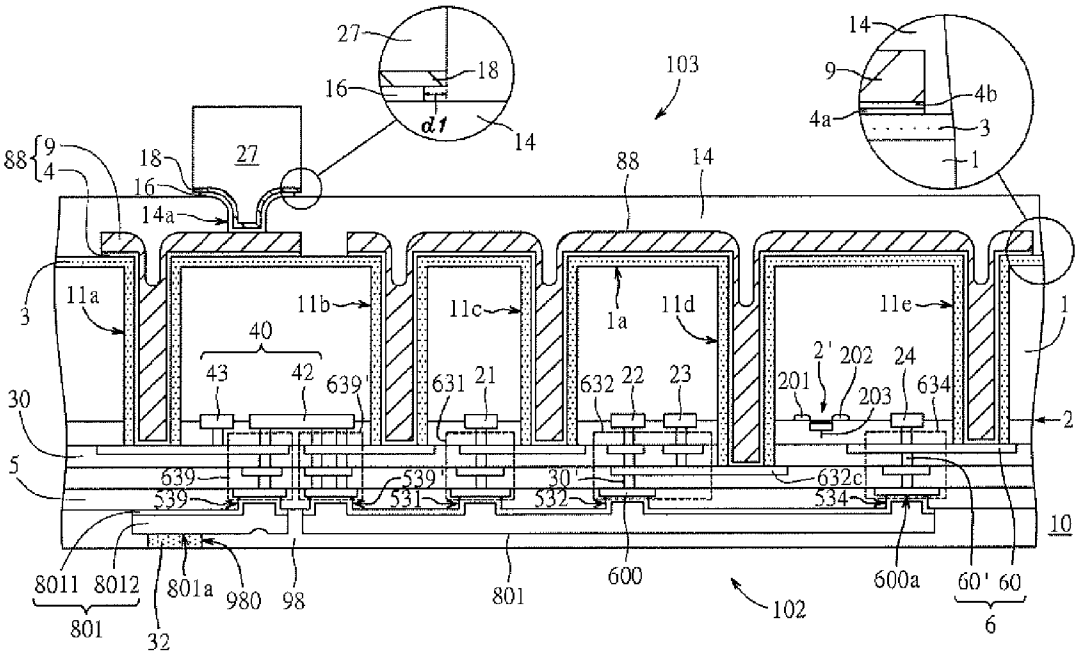


Fig. 25O

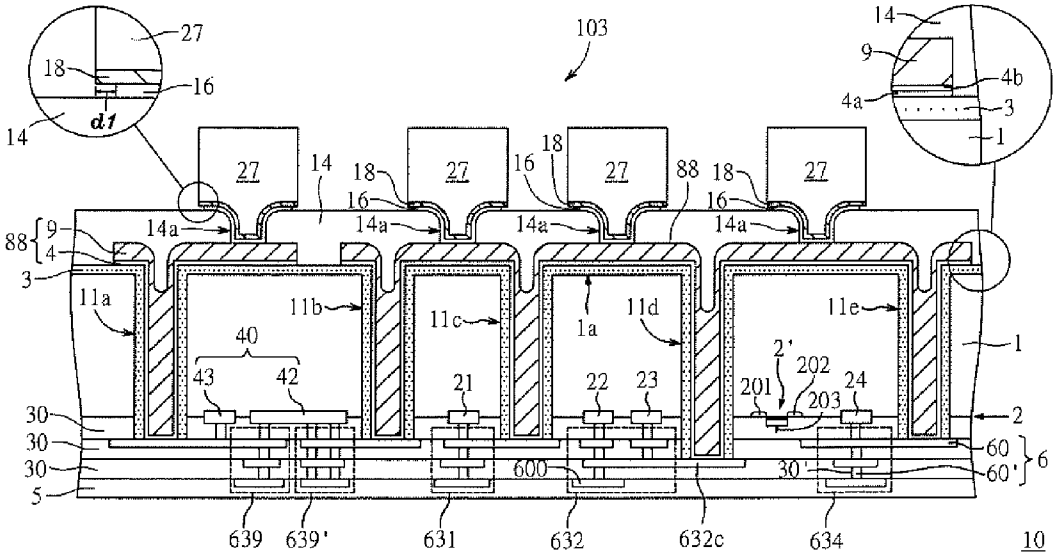


Fig. 25P

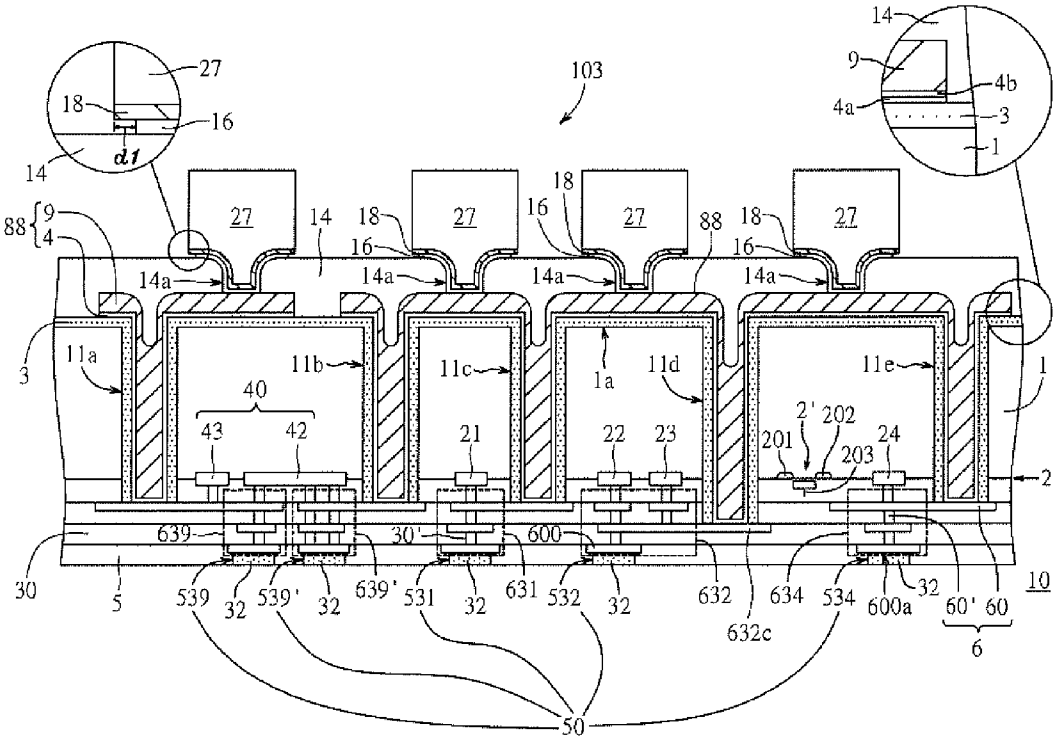


Fig. 25Q

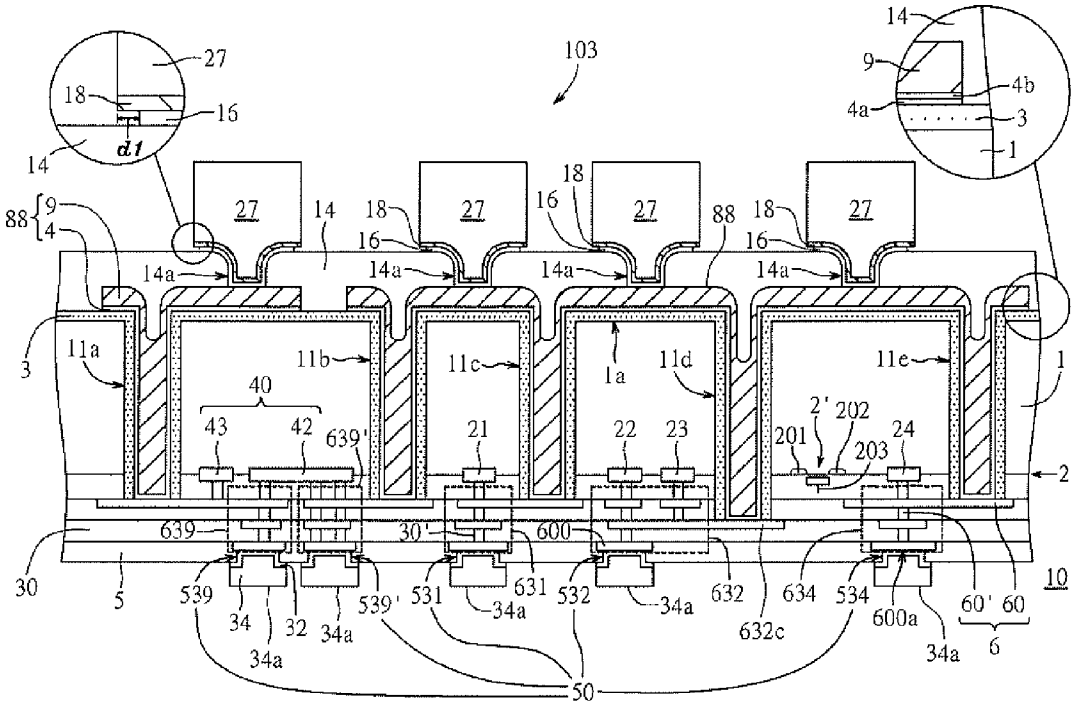


Fig. 25R

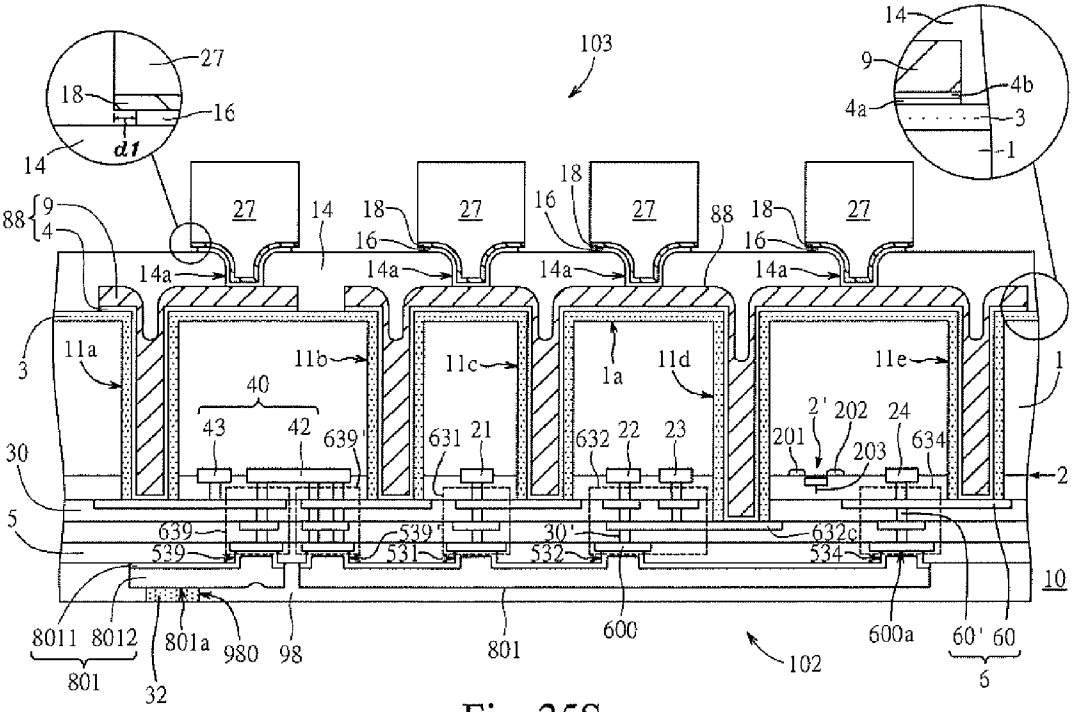


Fig. 25S

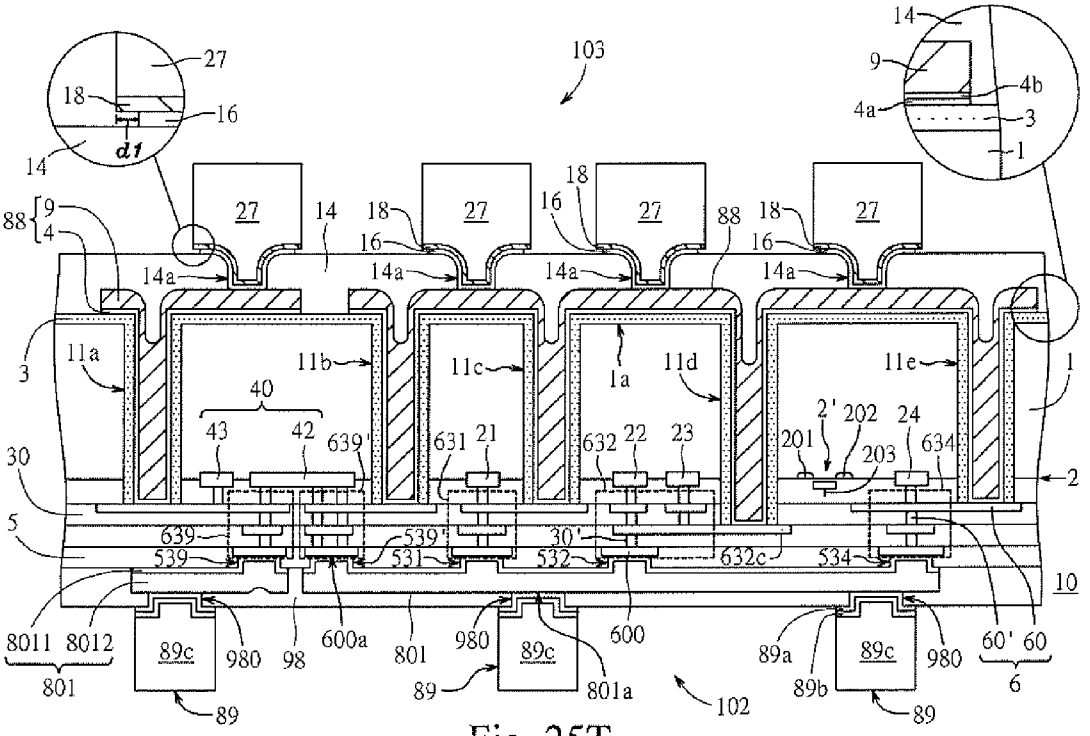


Fig. 25T

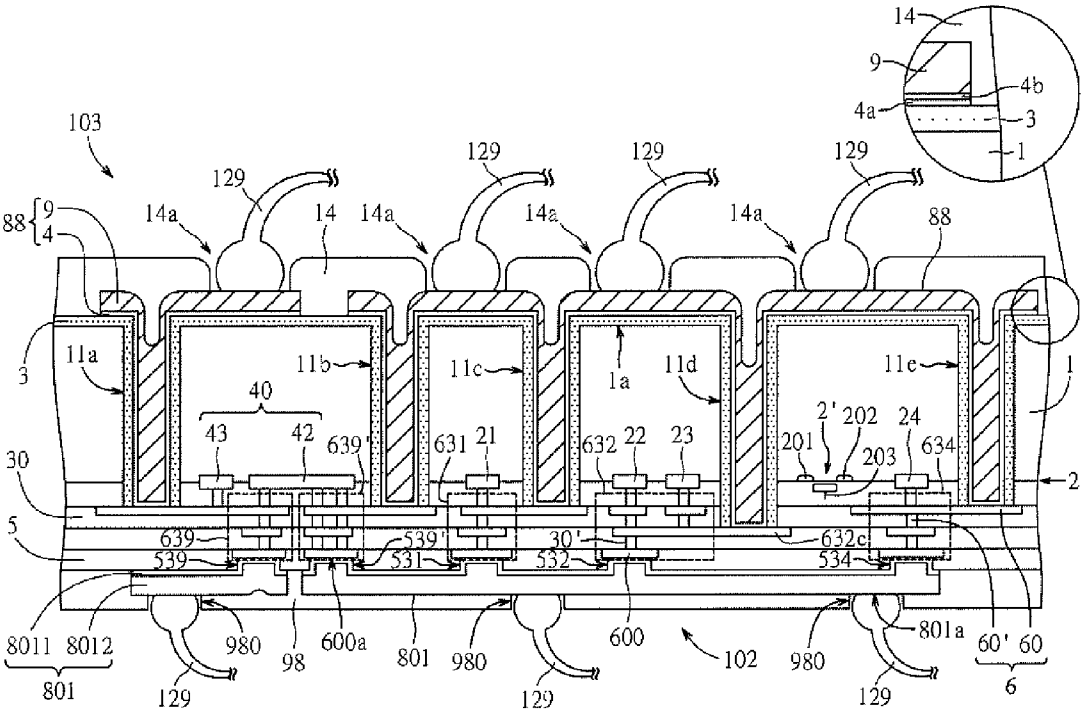


Fig. 25U

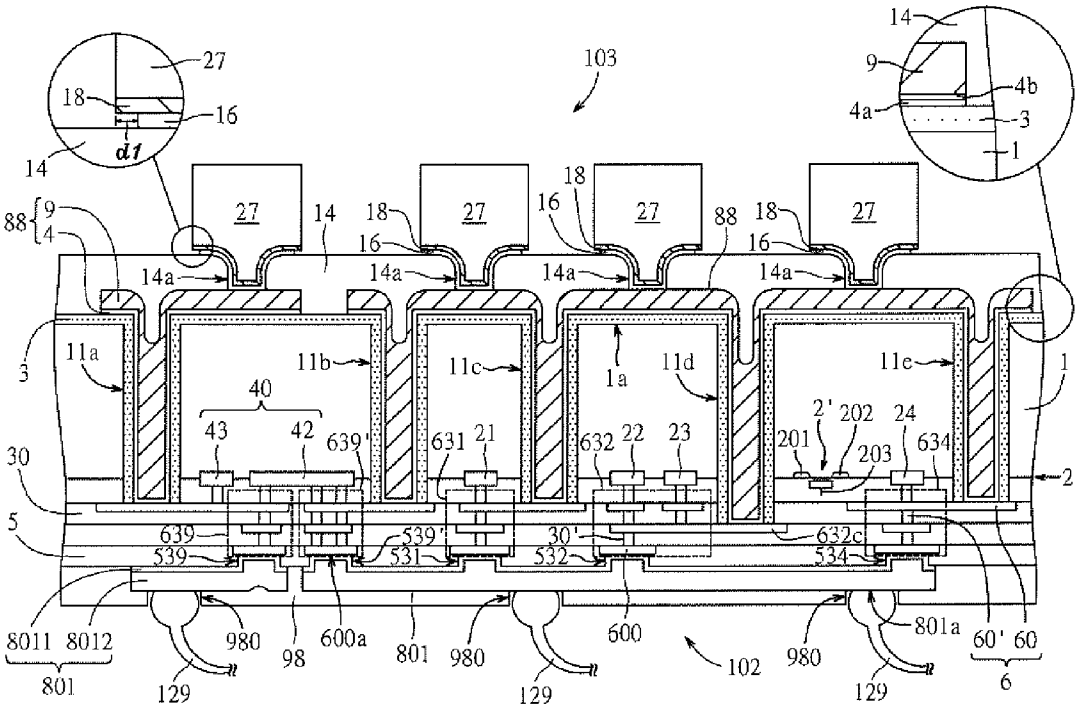


Fig. 25V

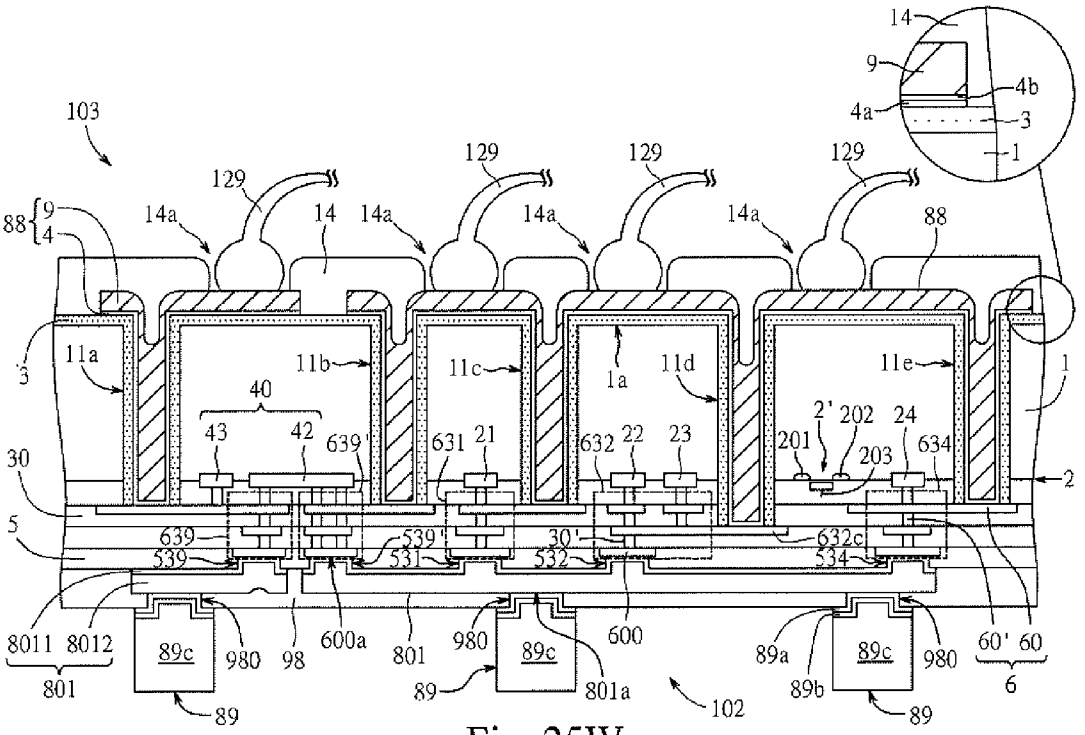


Fig. 25W

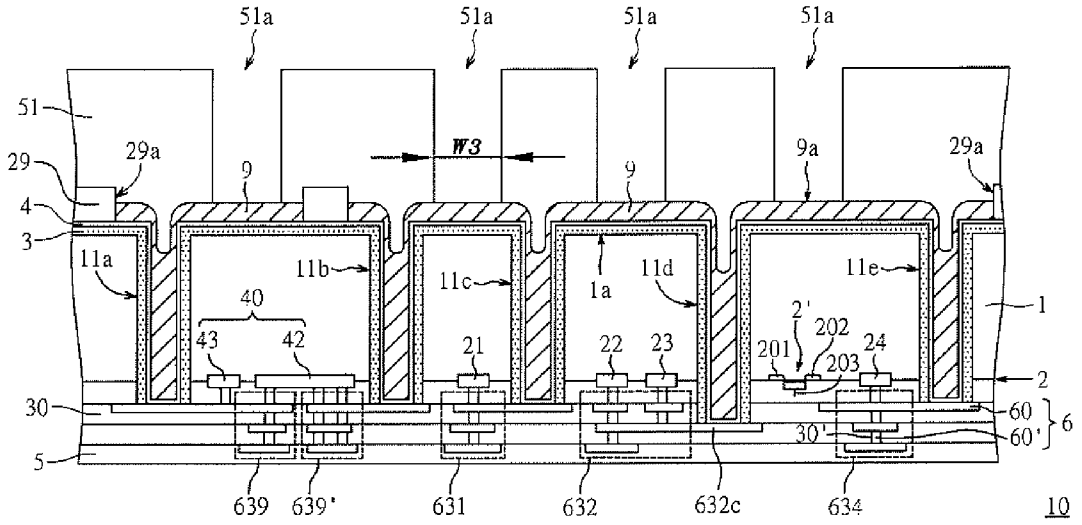


Fig. 26A

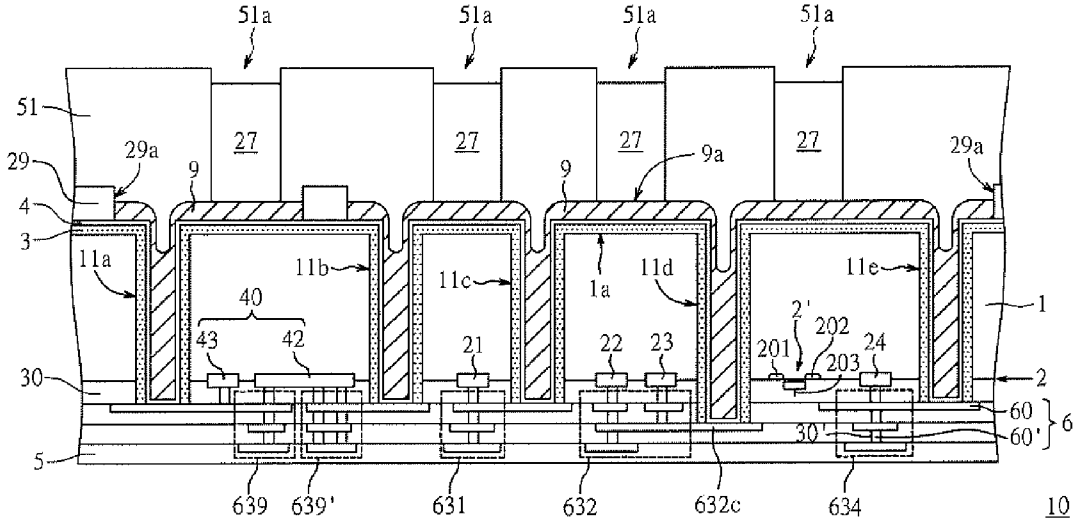


Fig. 26B

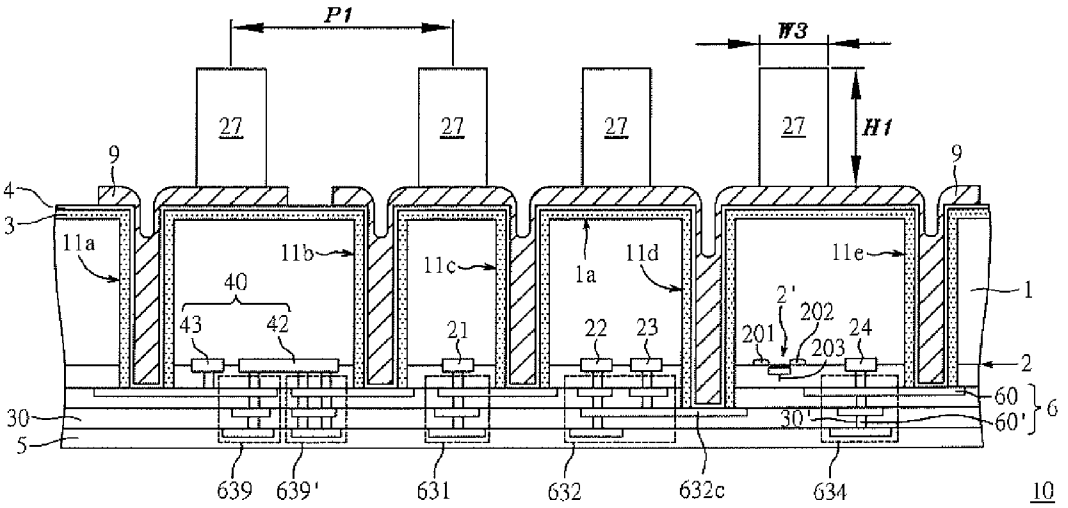


Fig. 26C

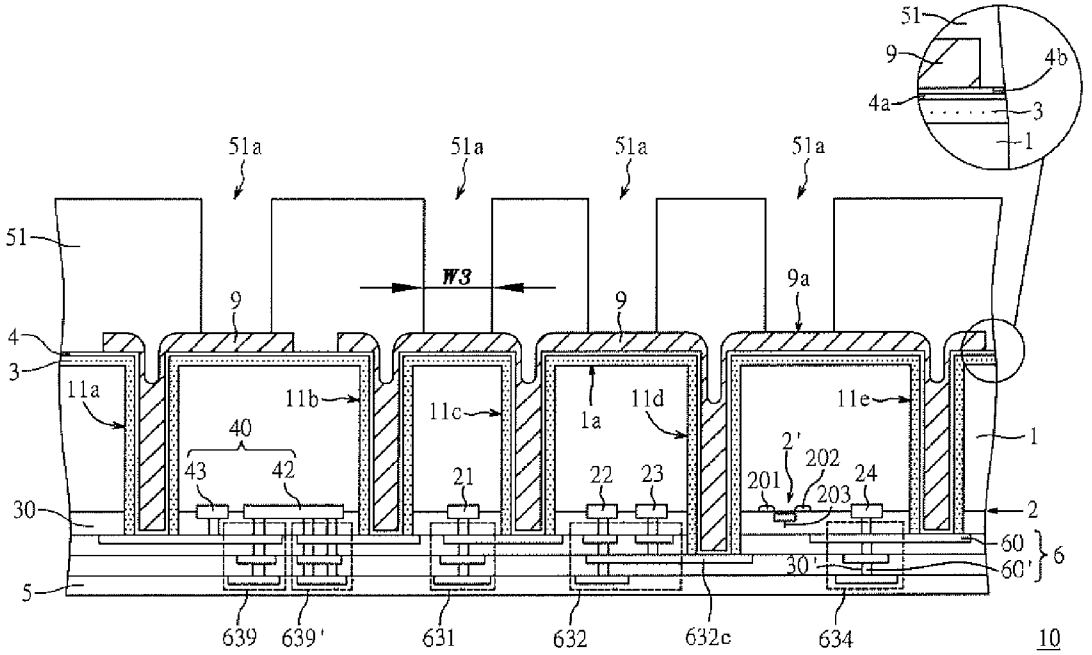


Fig. 26D

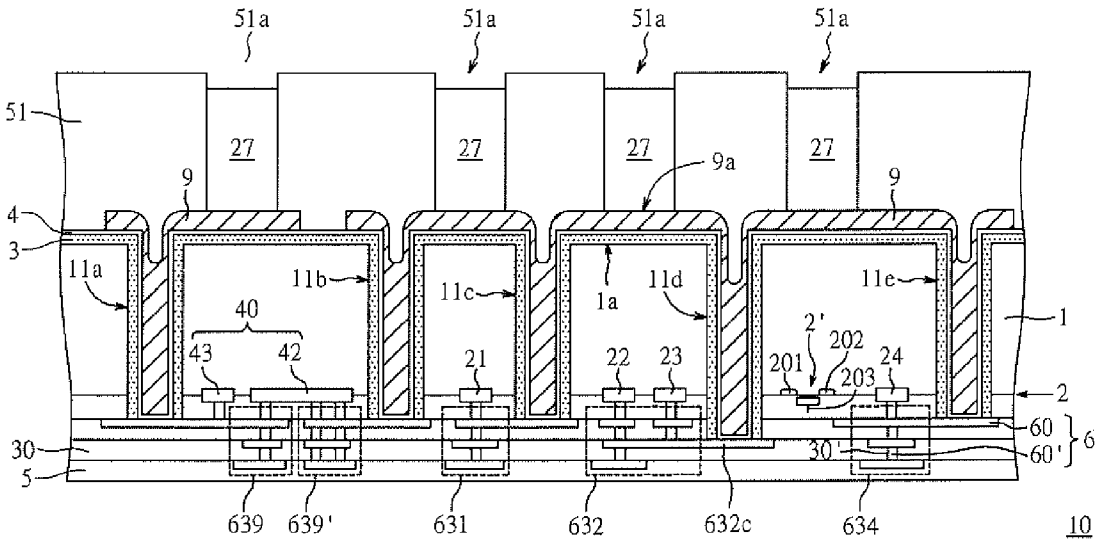


Fig. 26E

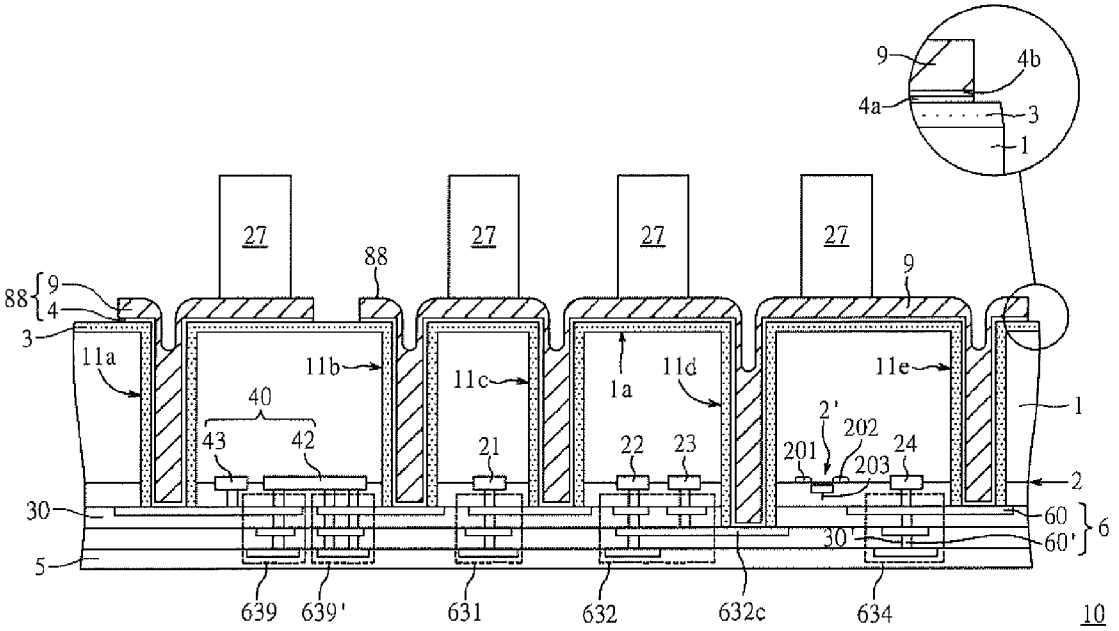


Fig. 26F

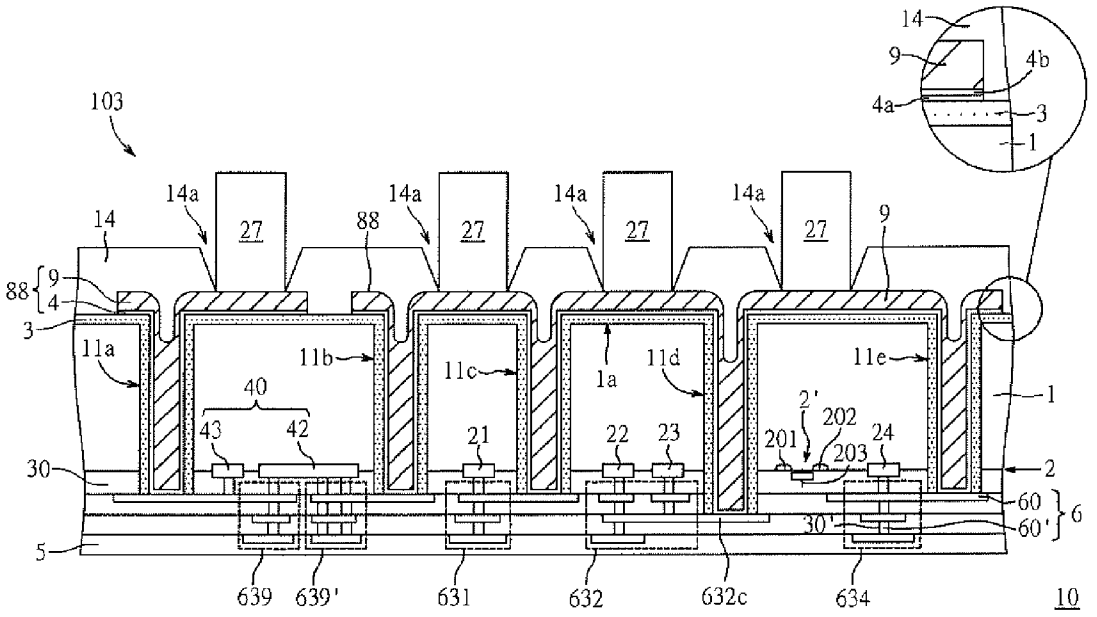


Fig. 26G

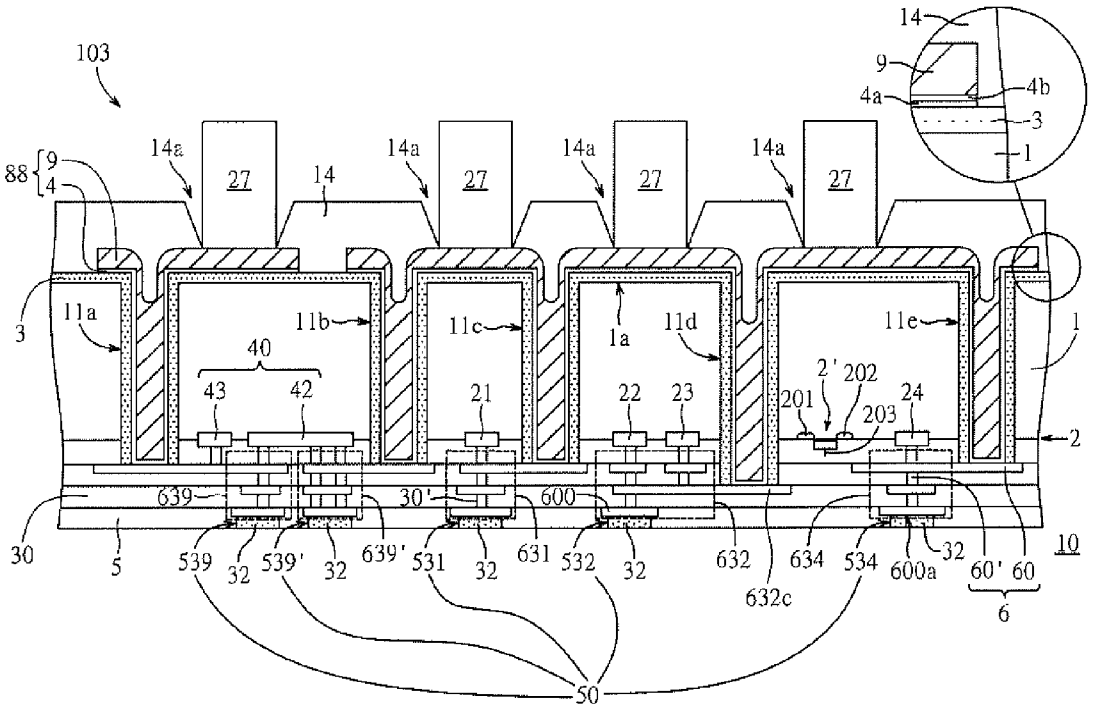


Fig. 26H

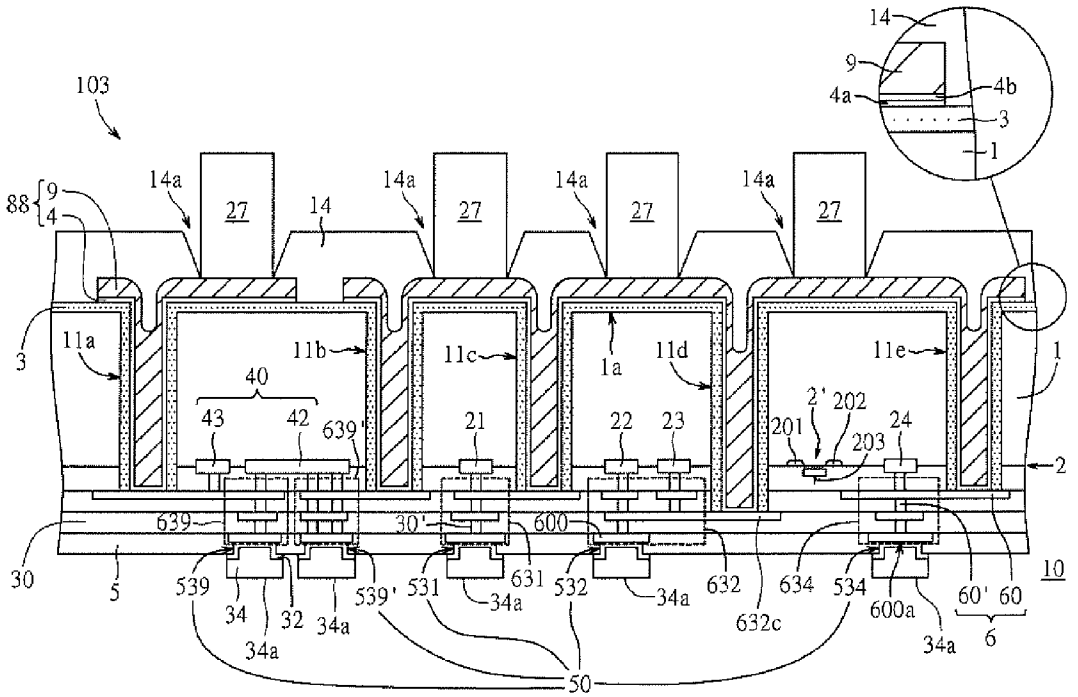


Fig. 26I

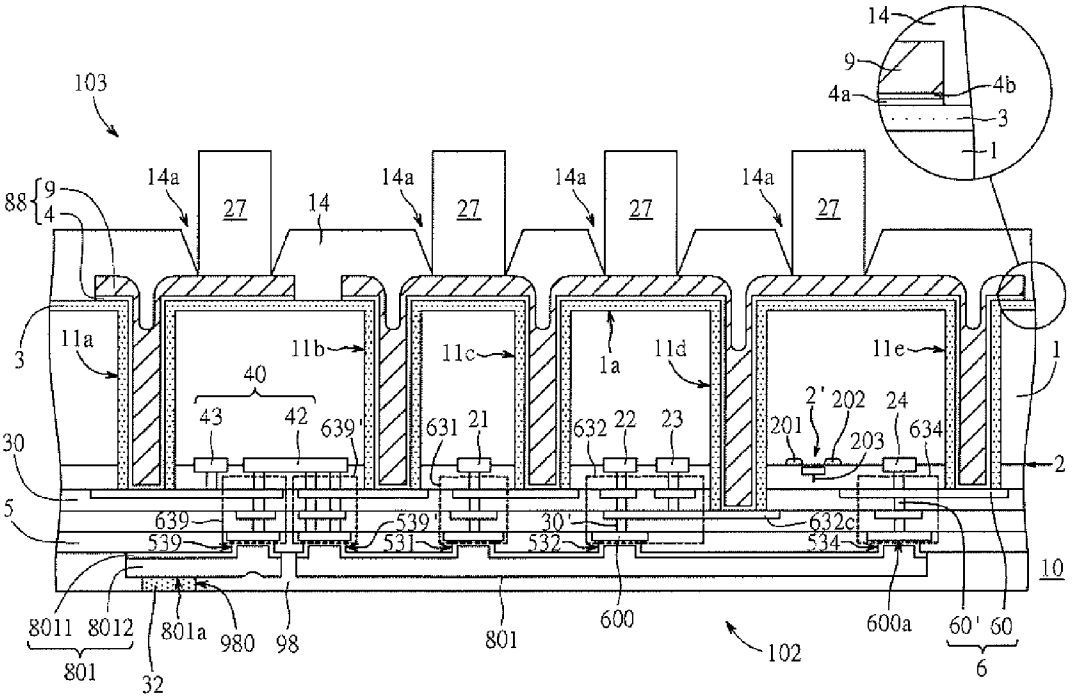


Fig. 26J

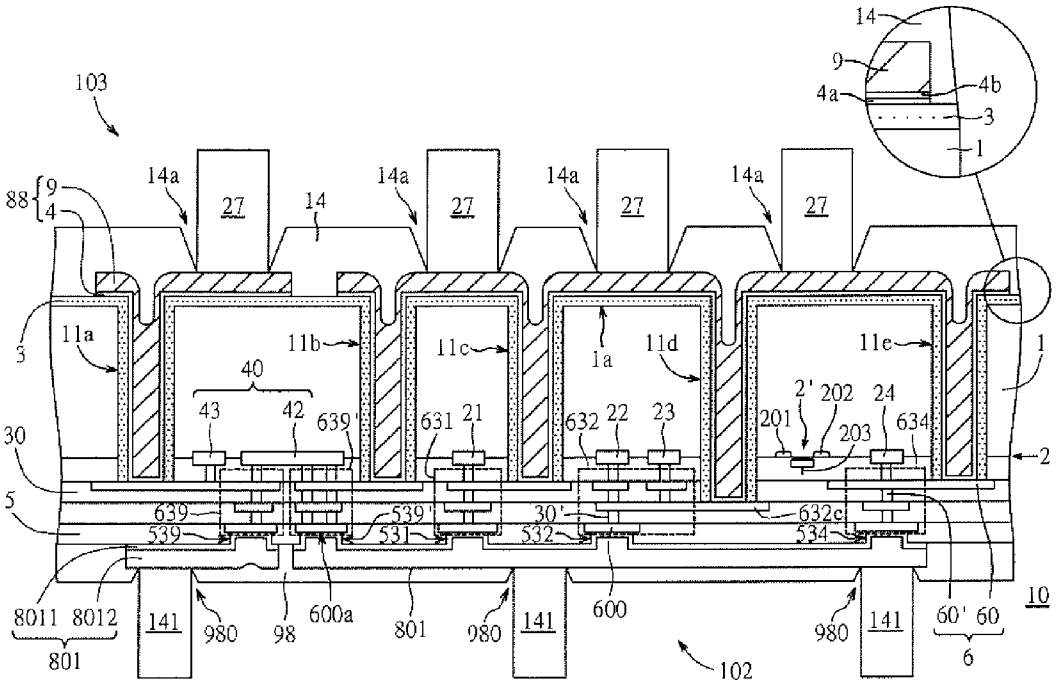


Fig. 26K

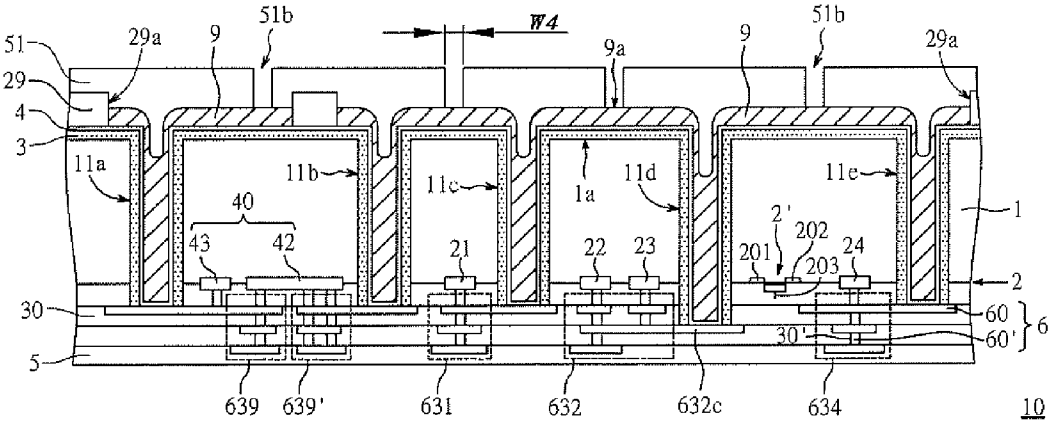


Fig. 27A

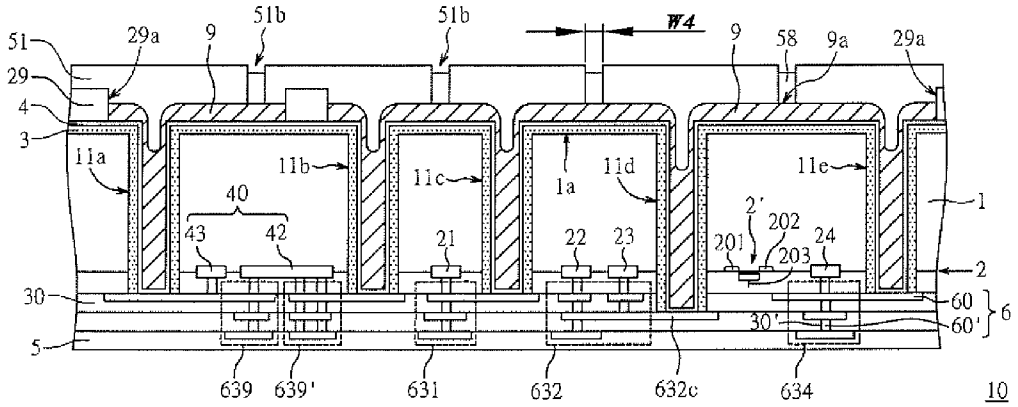


Fig. 27B

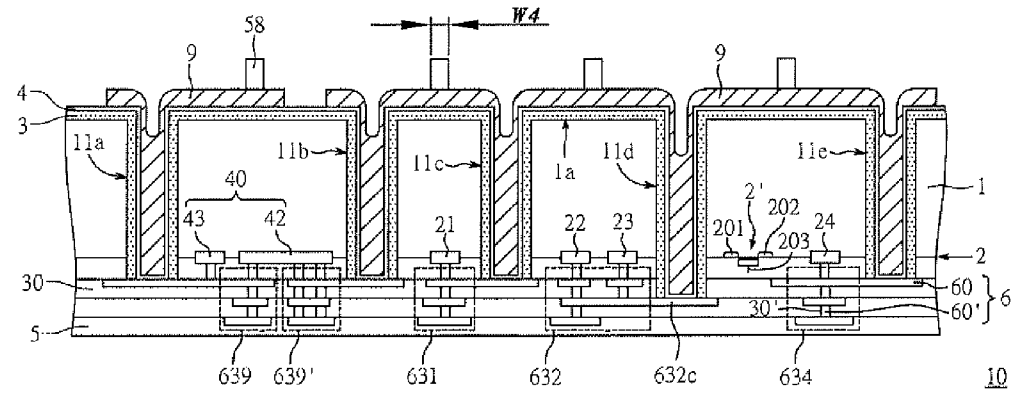


Fig. 27C

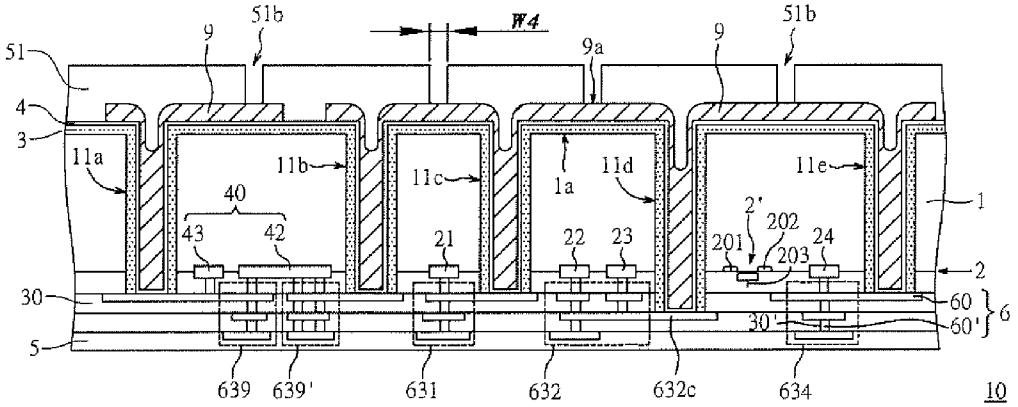


Fig. 27D

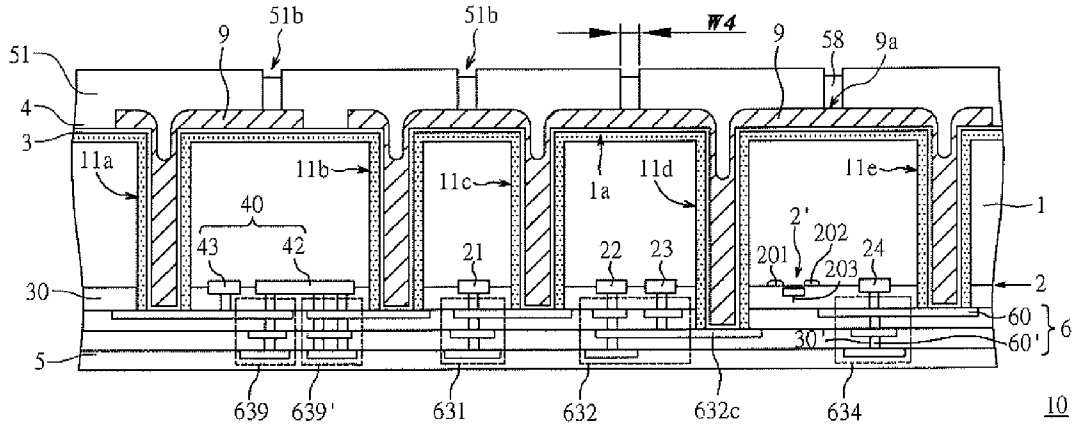


Fig. 27E

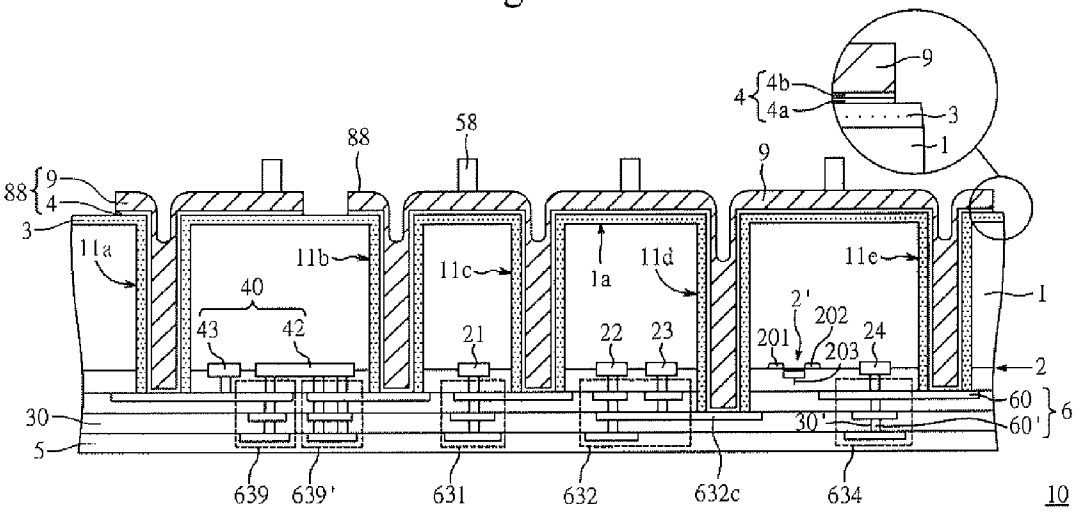


Fig. 27F

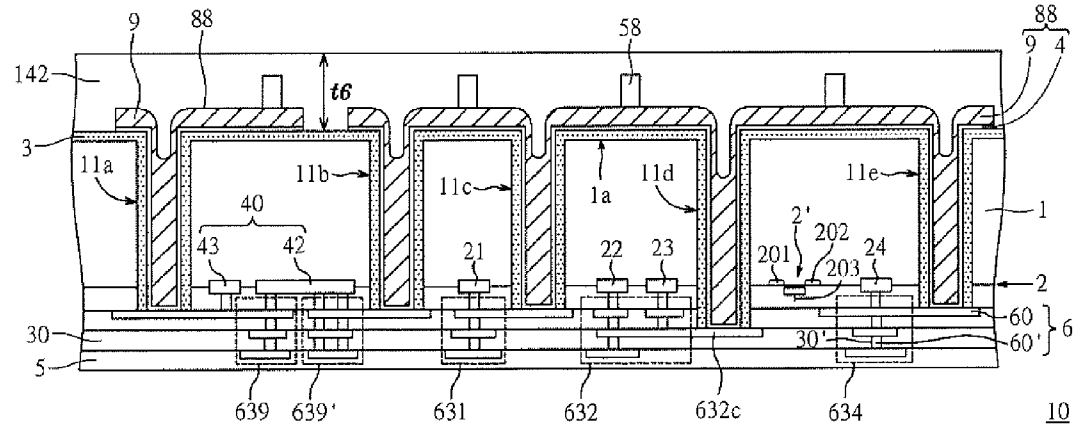


Fig. 27G

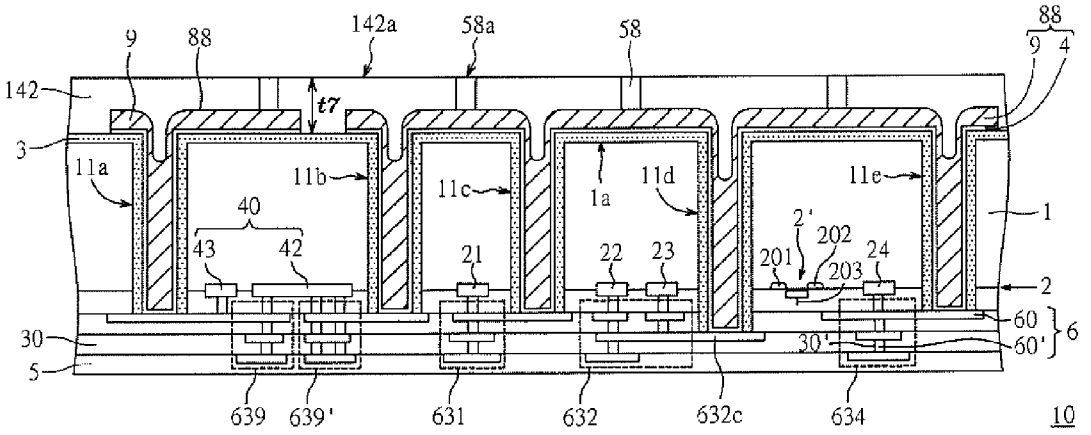


Fig. 27H

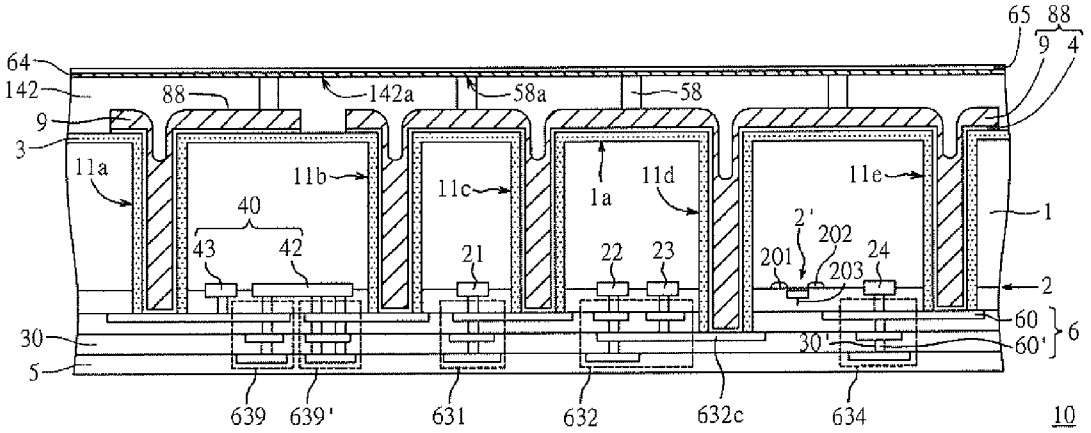


Fig. 27I

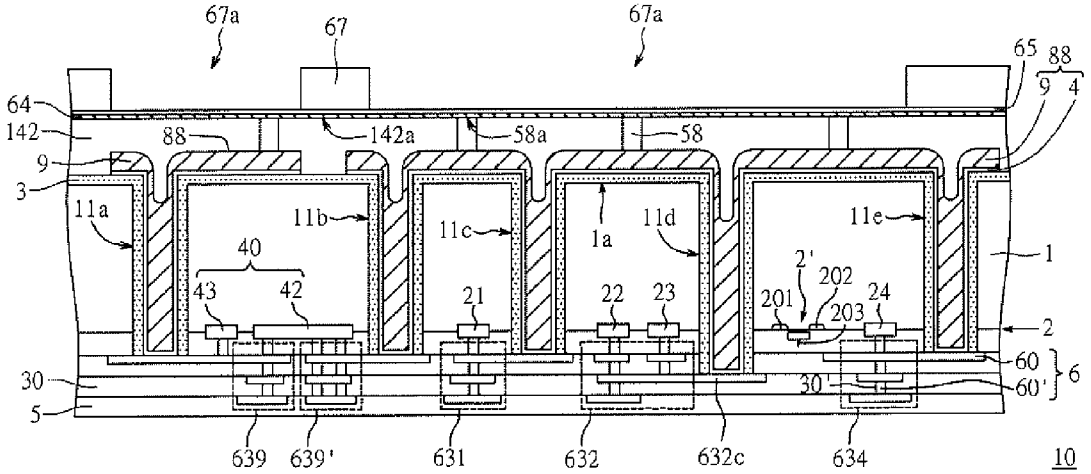


Fig. 27J

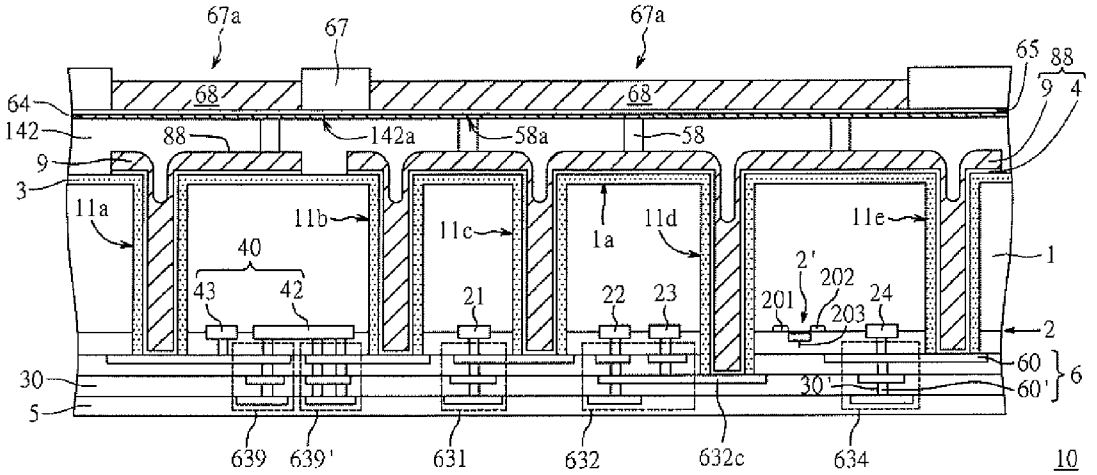


Fig. 27K

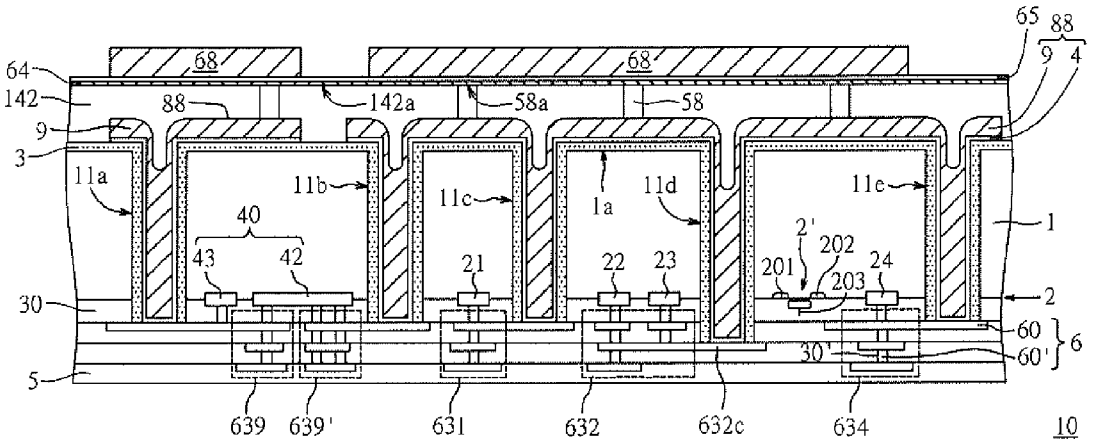


Fig. 27L

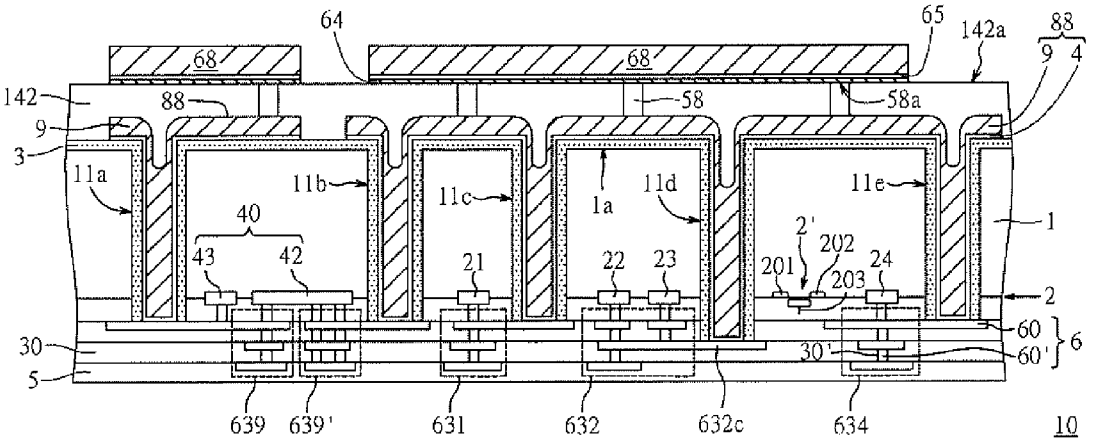


Fig. 27M

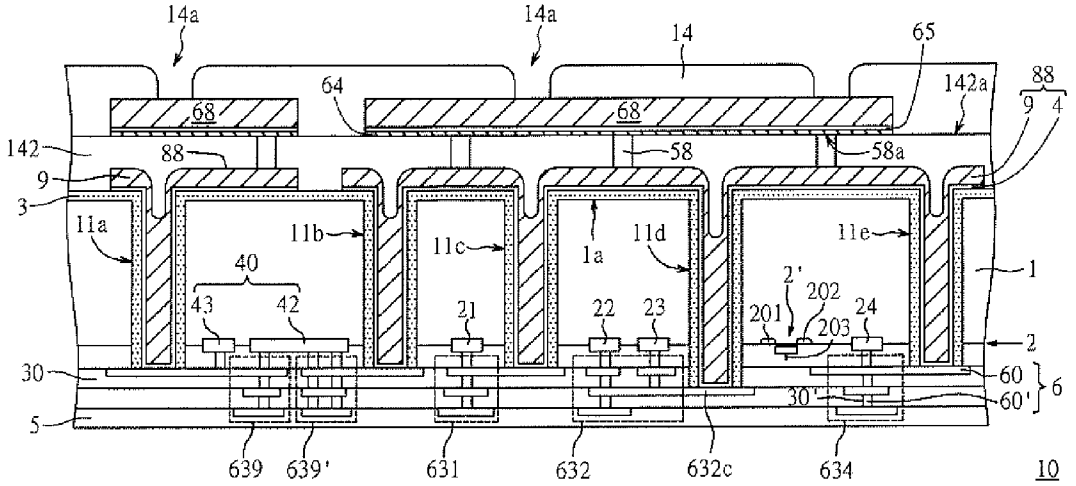


Fig. 27N

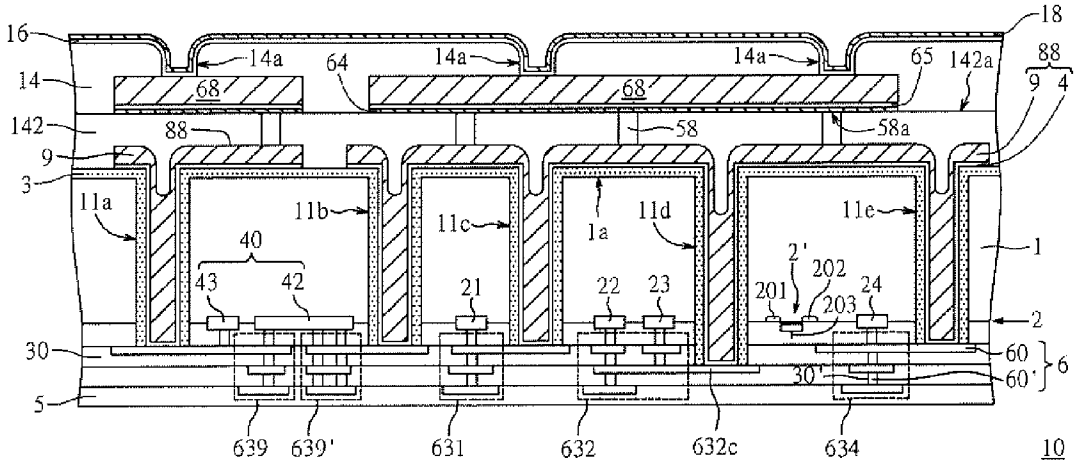


Fig. 27O

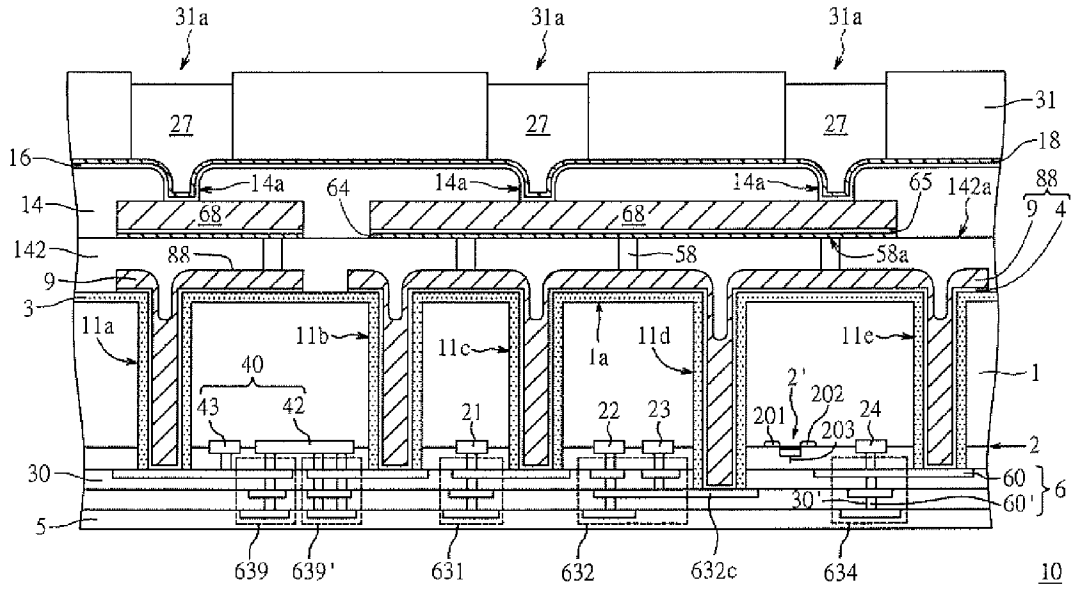


Fig. 27P

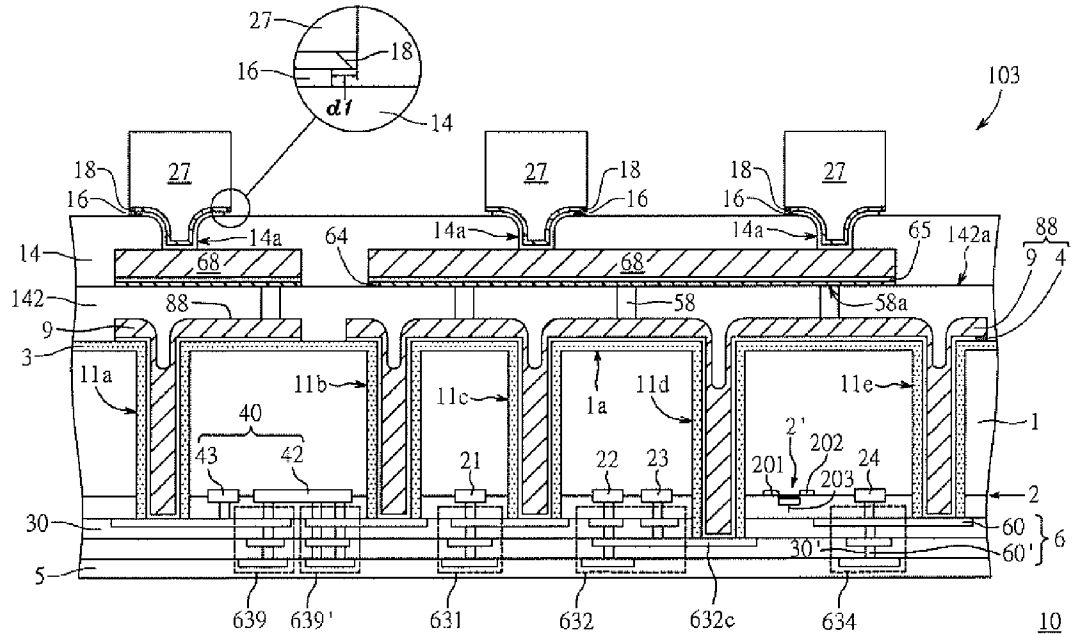


Fig. 27Q

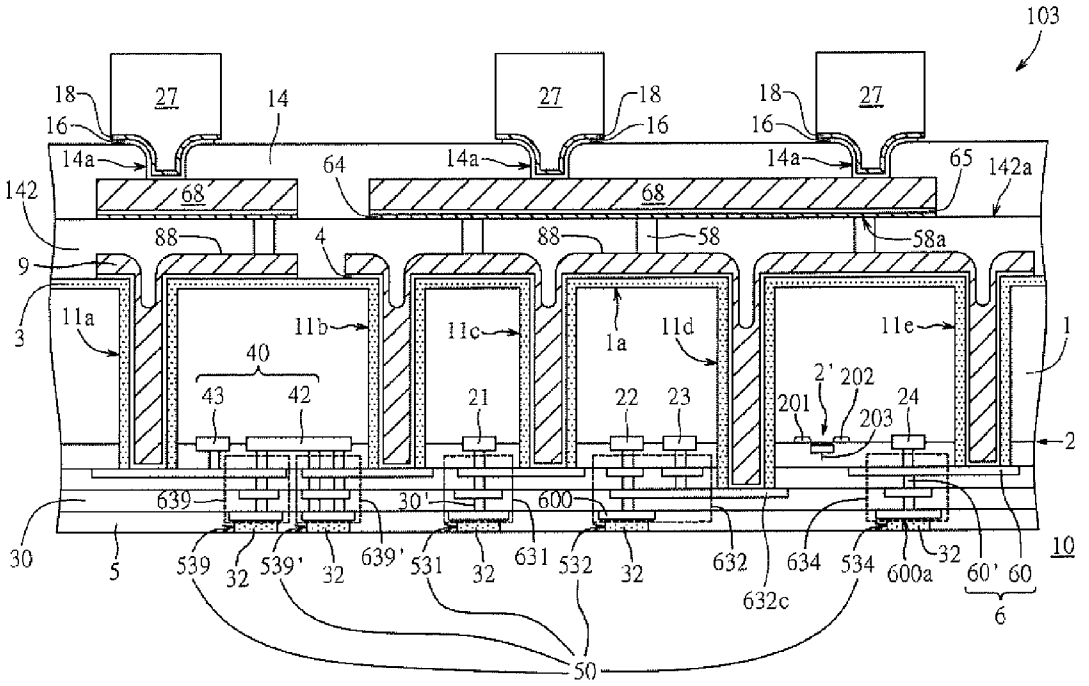


Fig. 27R

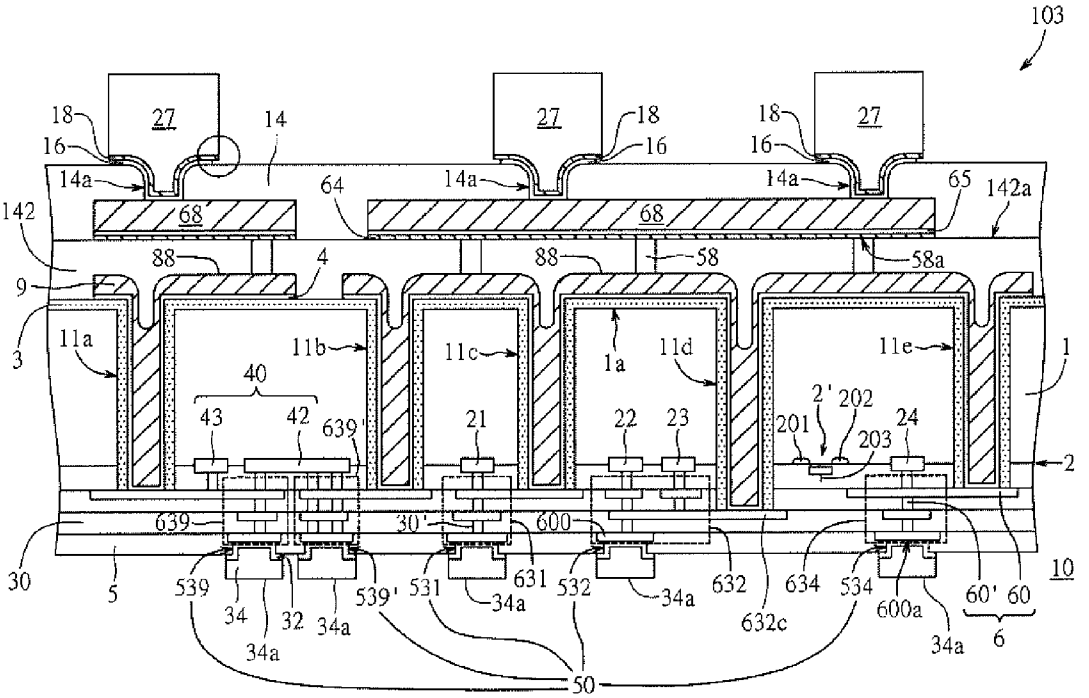


Fig. 27S

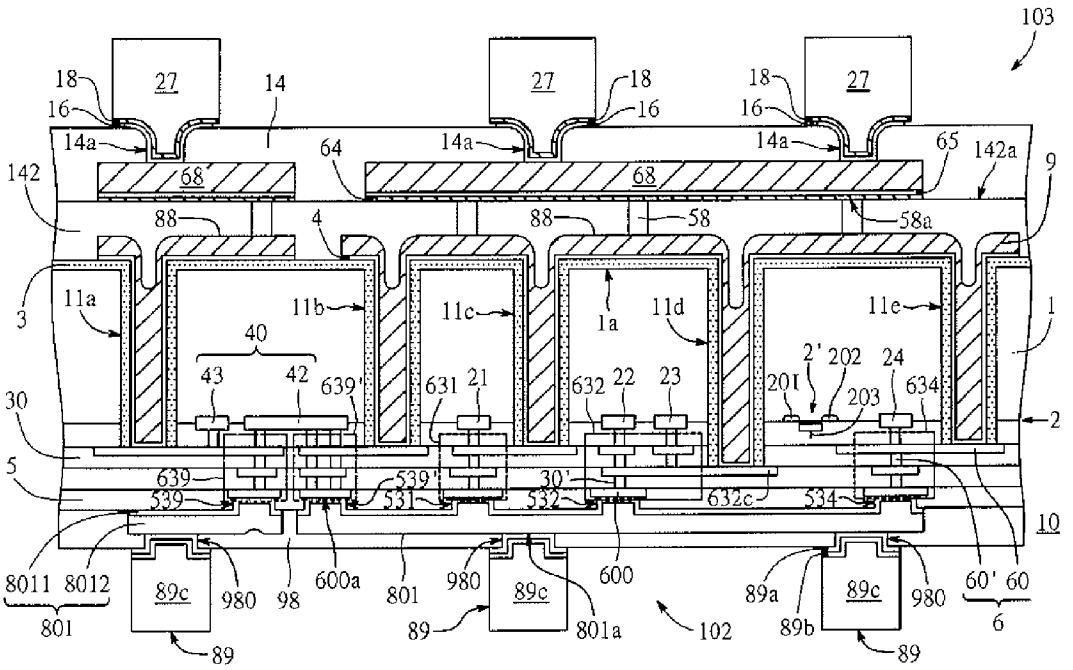


Fig. 27T

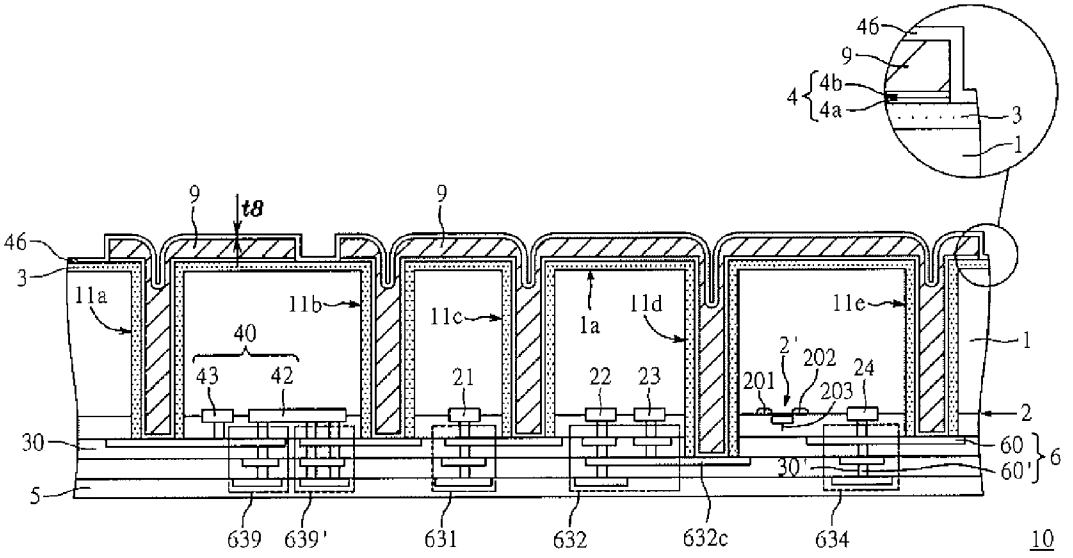


Fig. 28A

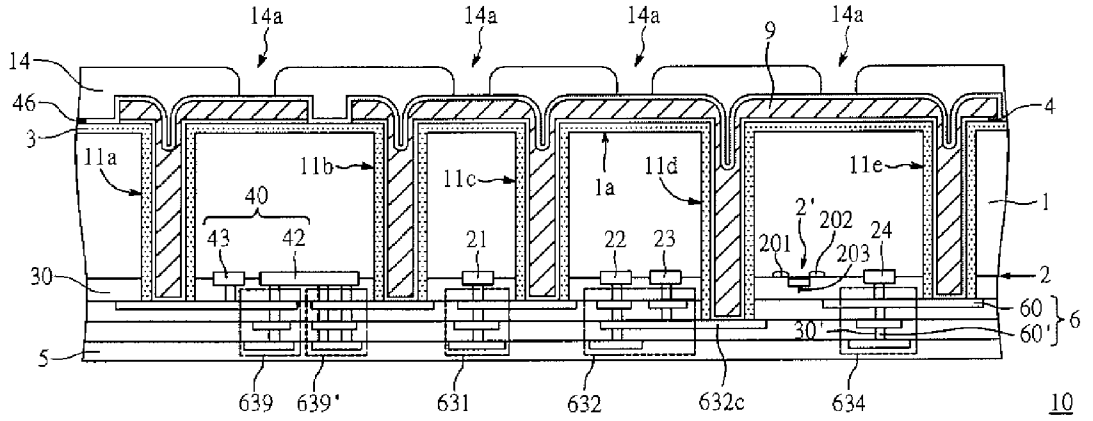


Fig. 28B

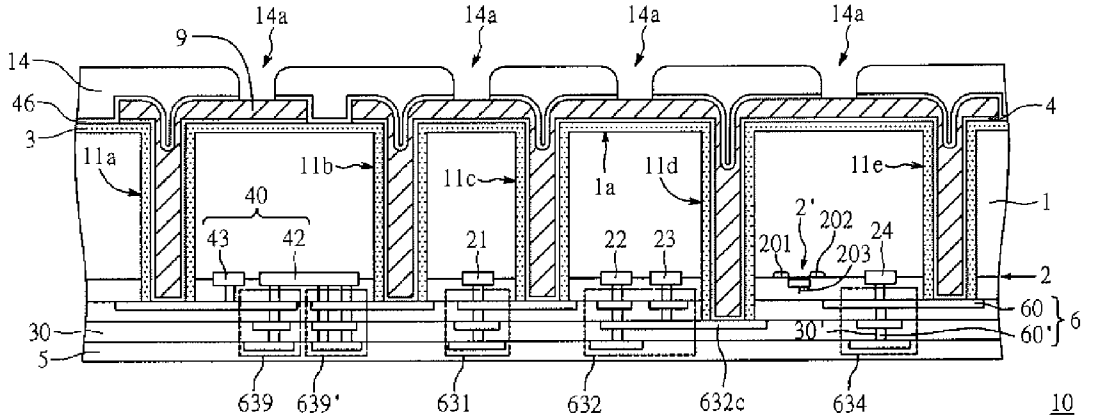


Fig. 28C

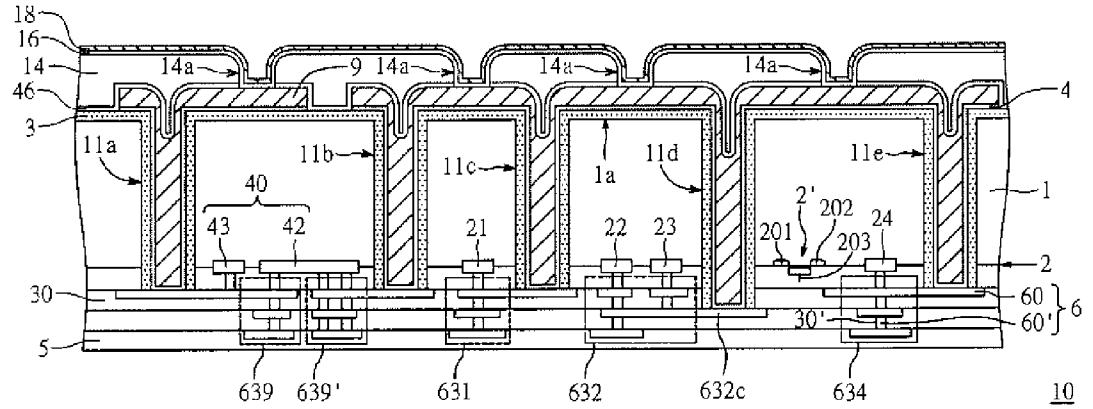


Fig. 28D

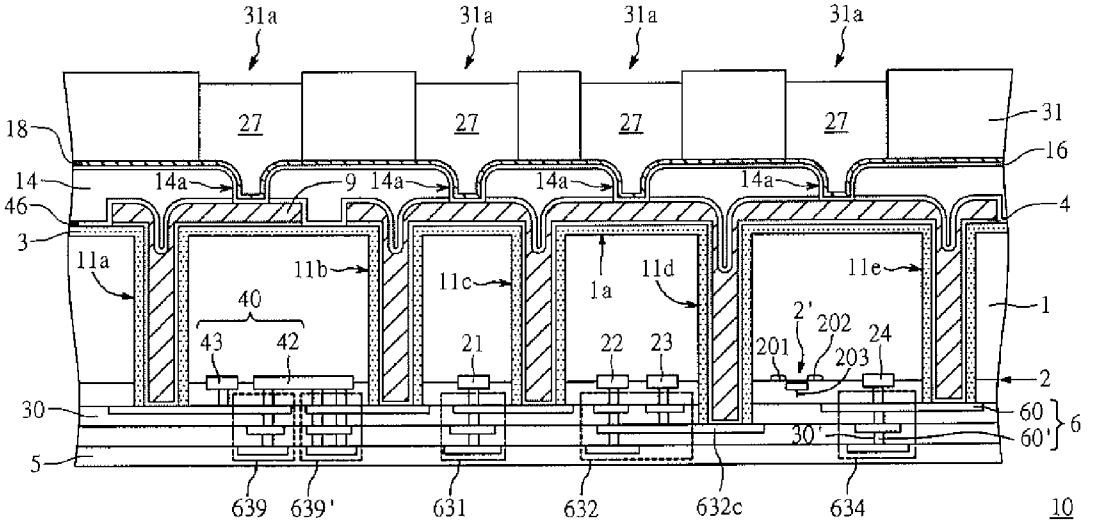


Fig. 28E

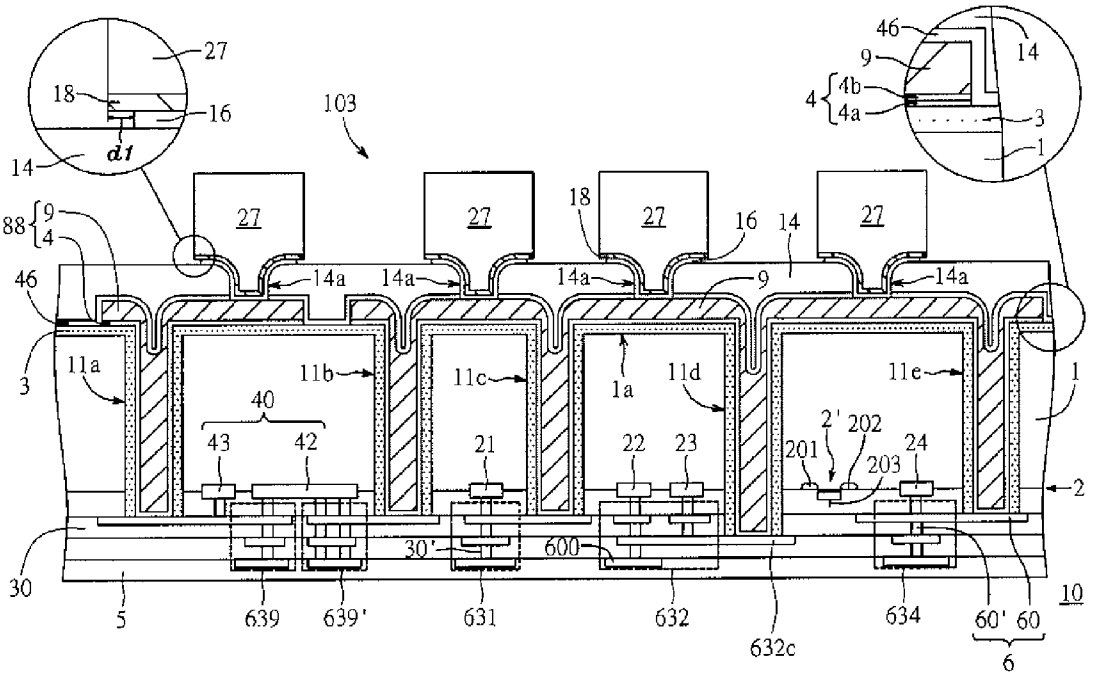


Fig. 28F

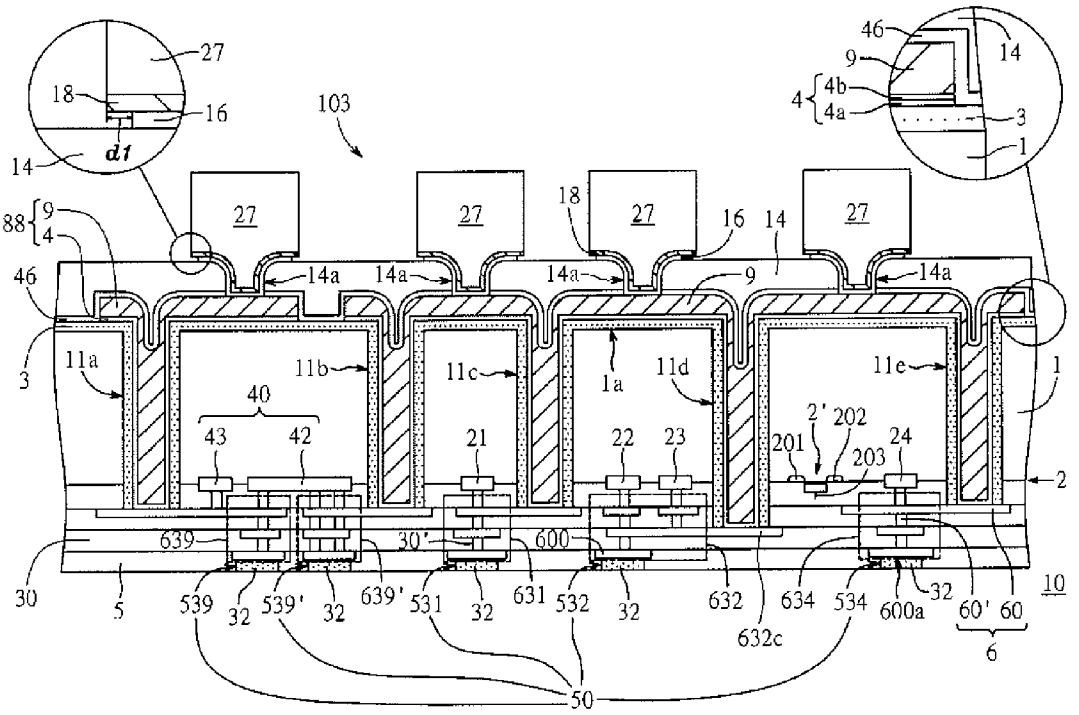


Fig. 28G

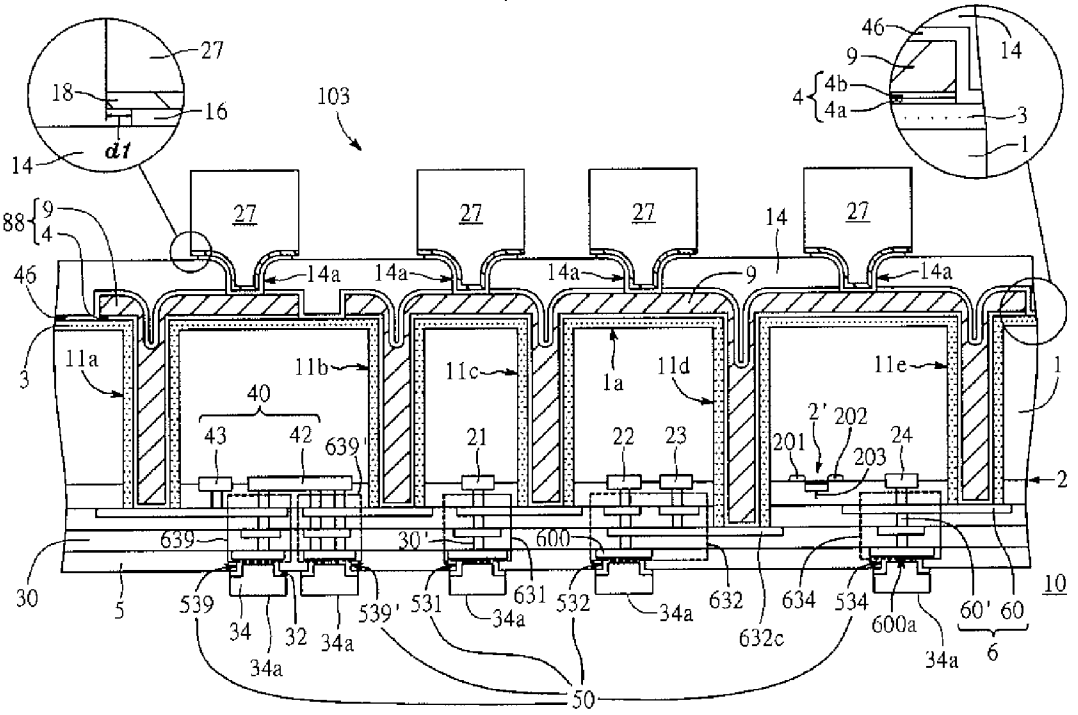


Fig. 28H

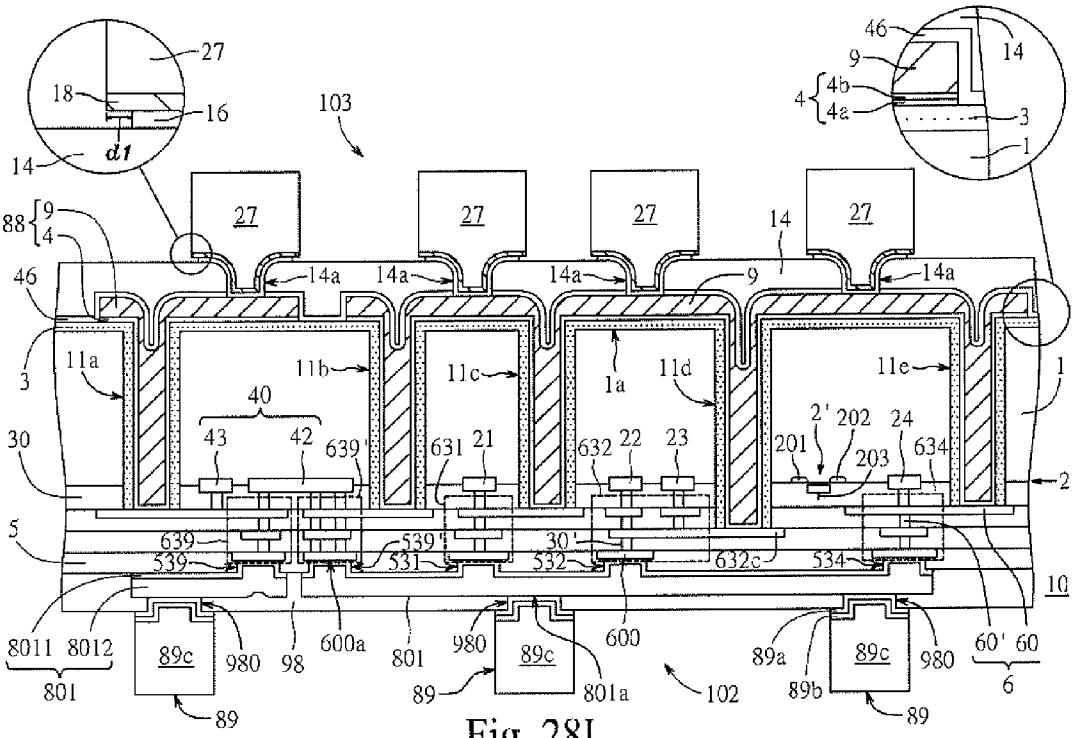


Fig. 28I

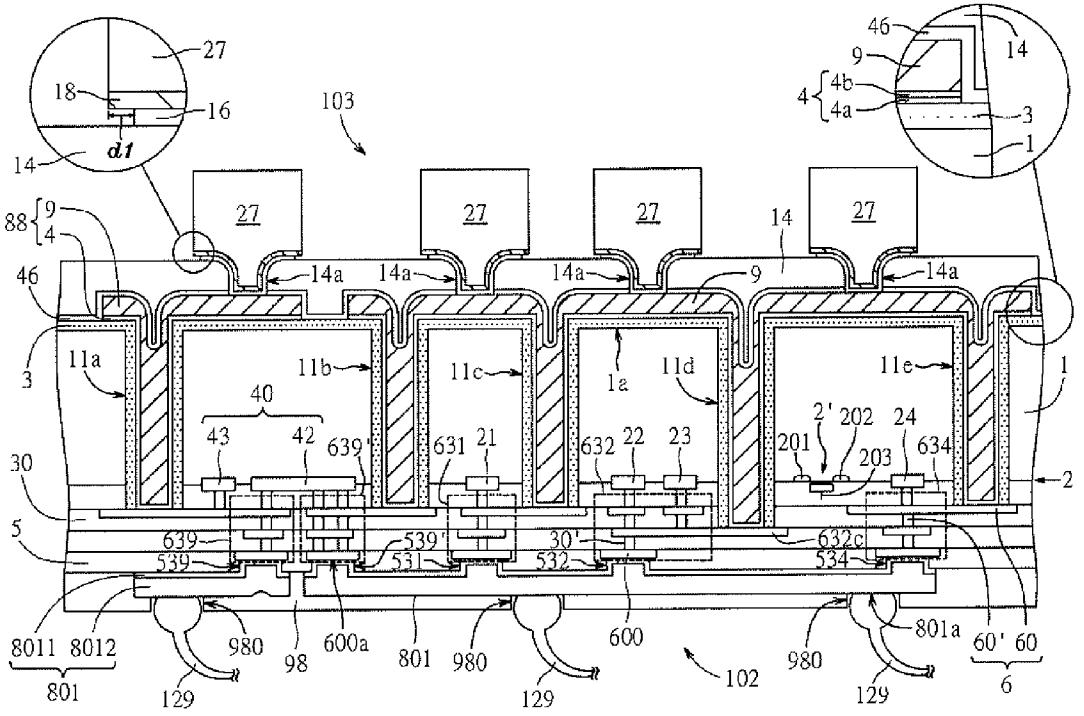


Fig. 28J

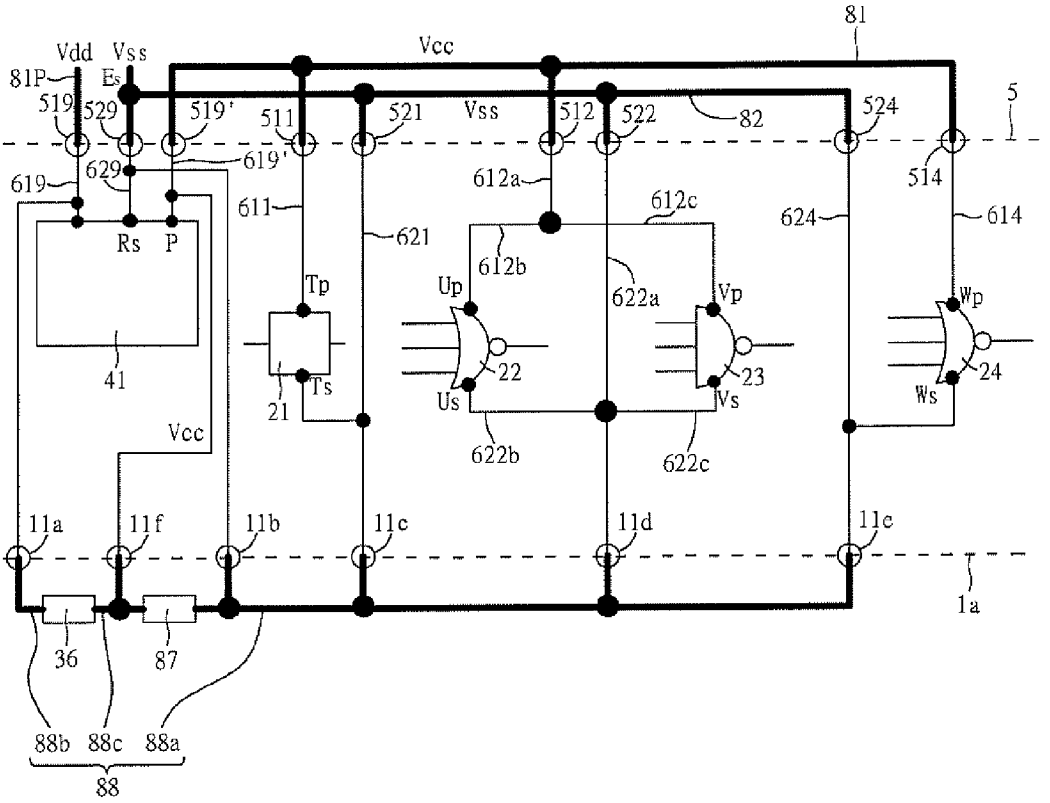

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Vdd
Vss
Vcc
81P
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619'
612a
612c
624
614
514
611
621
612b
622a
Rs
P
Tp
Up
Vp
Wp
41
Ts
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23
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88b
88c
88a
88

Fig. 29A

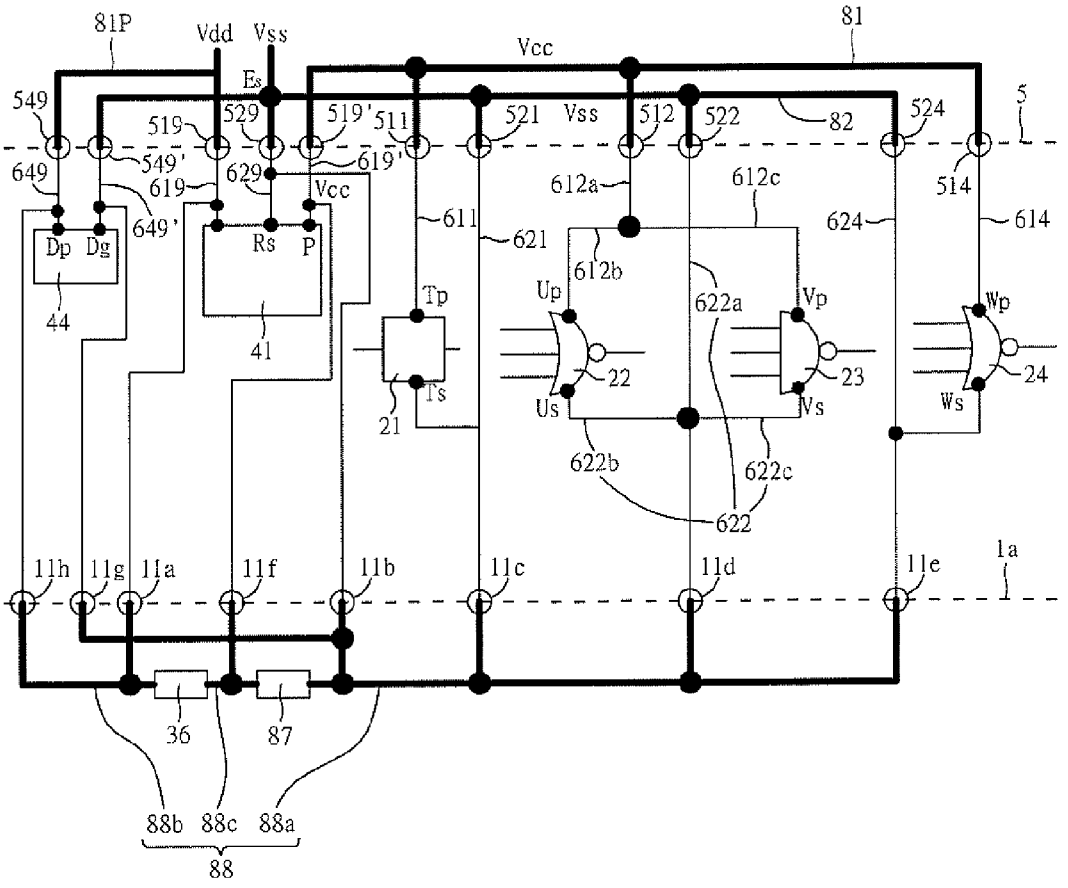

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Vcc
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612c
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Dp
Dg
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Vp
Wp
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Us
Vs
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Fig. 29B

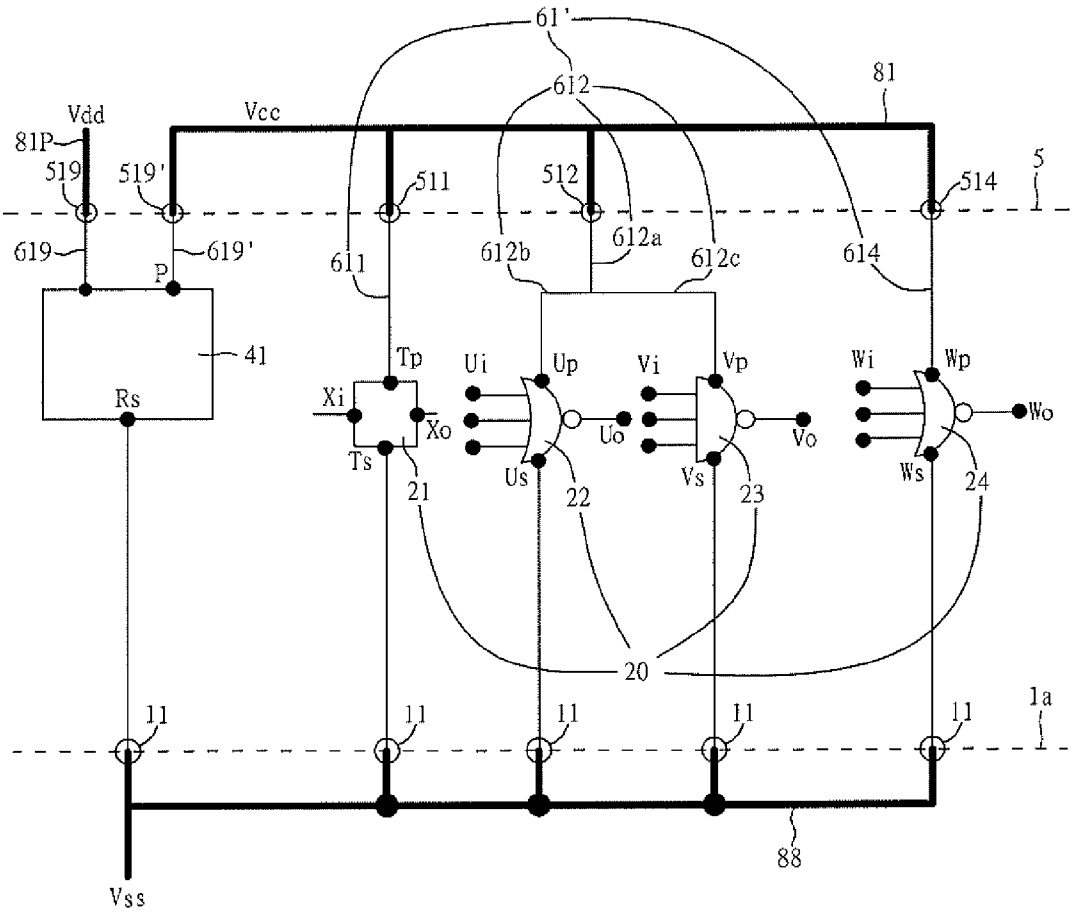

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612b
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Tp
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Vi
Vp
Wi
Wp
Rs
Xi
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Ws
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20
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1a
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Vss

Fig. 29C

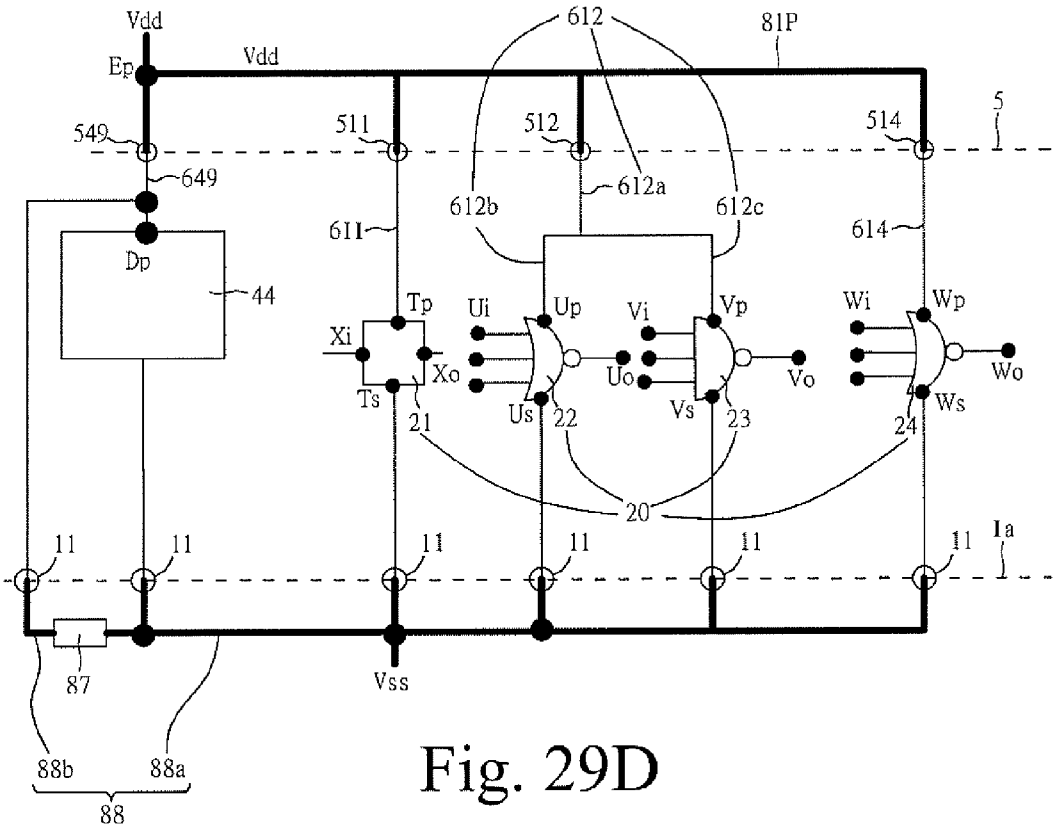

Vdd
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649
612b
612a
612c
611
614
Dp
44
Tp
Ui
Up
Vi
Vp
Wi
Wp
Xi
Xo
Uo
Vo
Wo
Ts
21
Us
22
Vs
23
24
Ws
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11
11
11
11
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11
Ia
87
Vss
88b
88a
88

Fig. 29D

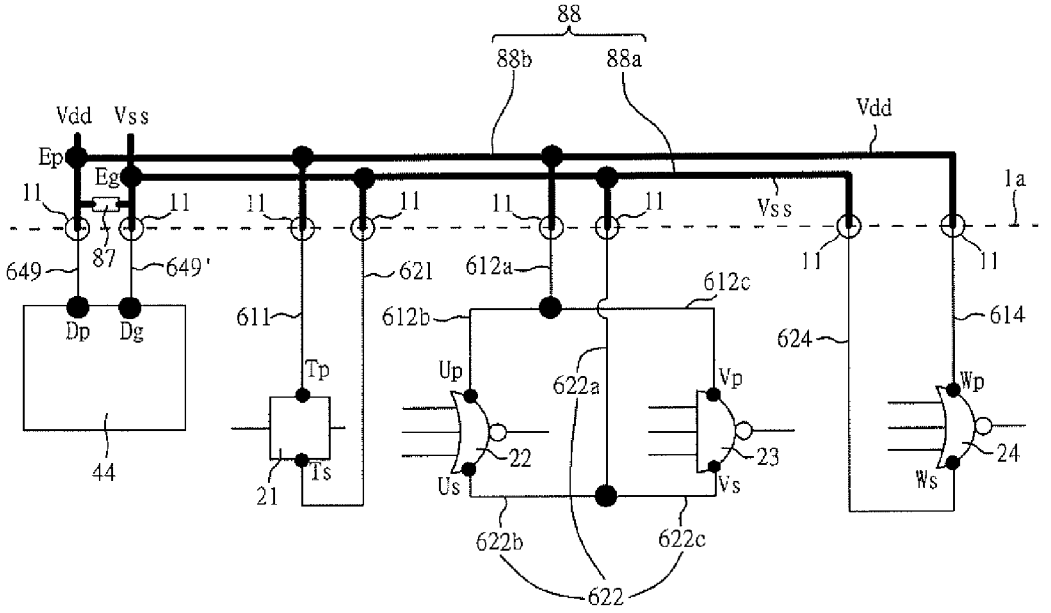


Fig. 29E

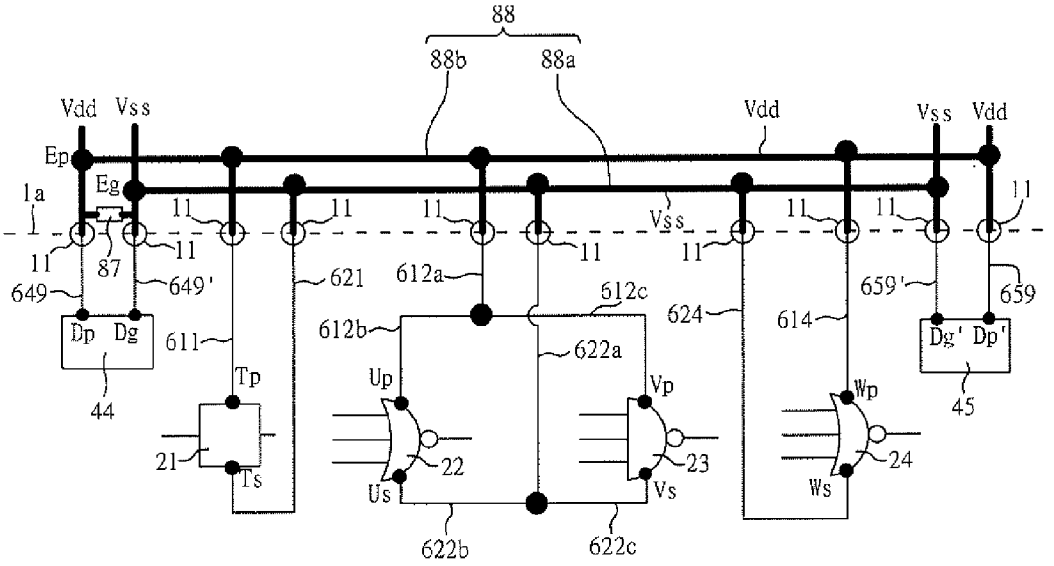


Fig. 29F

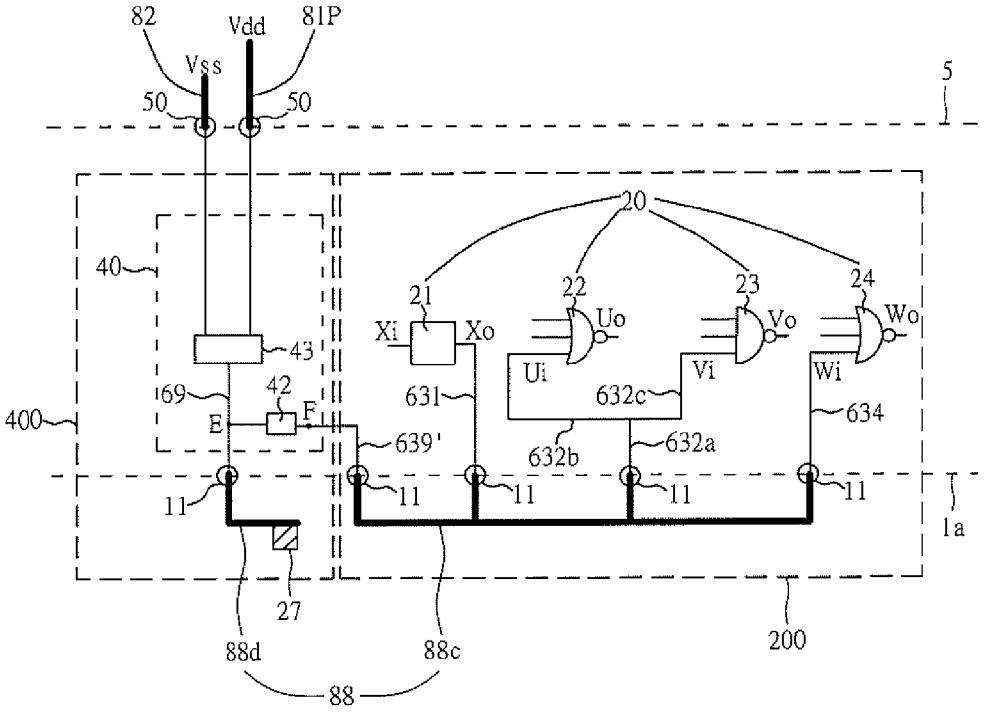


Fig. 29G

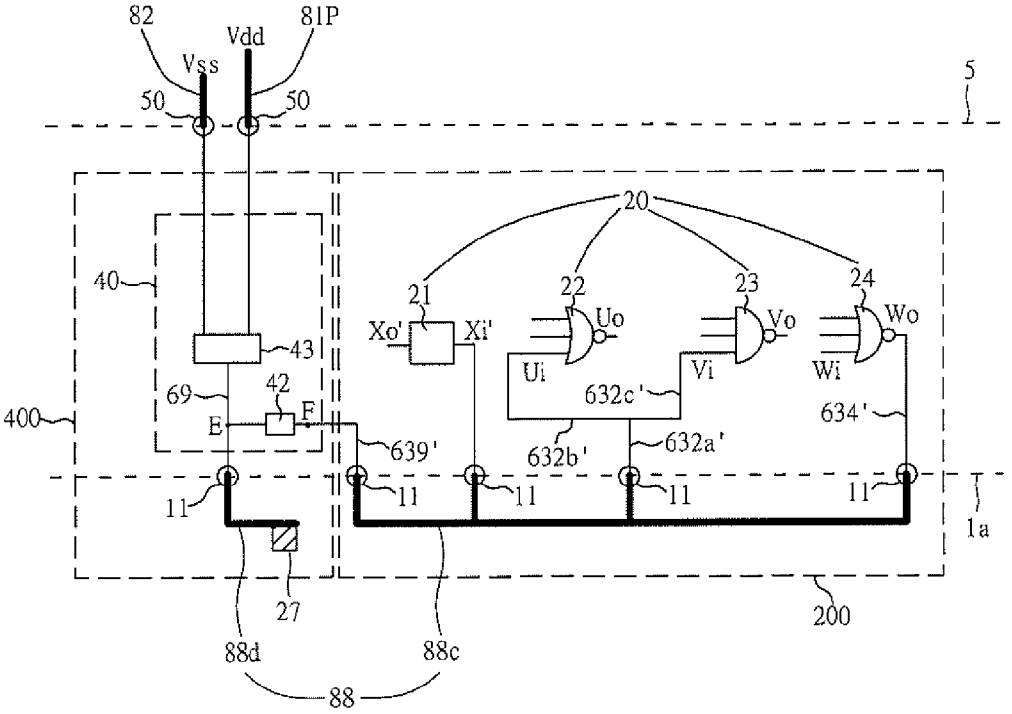


Fig. 29H

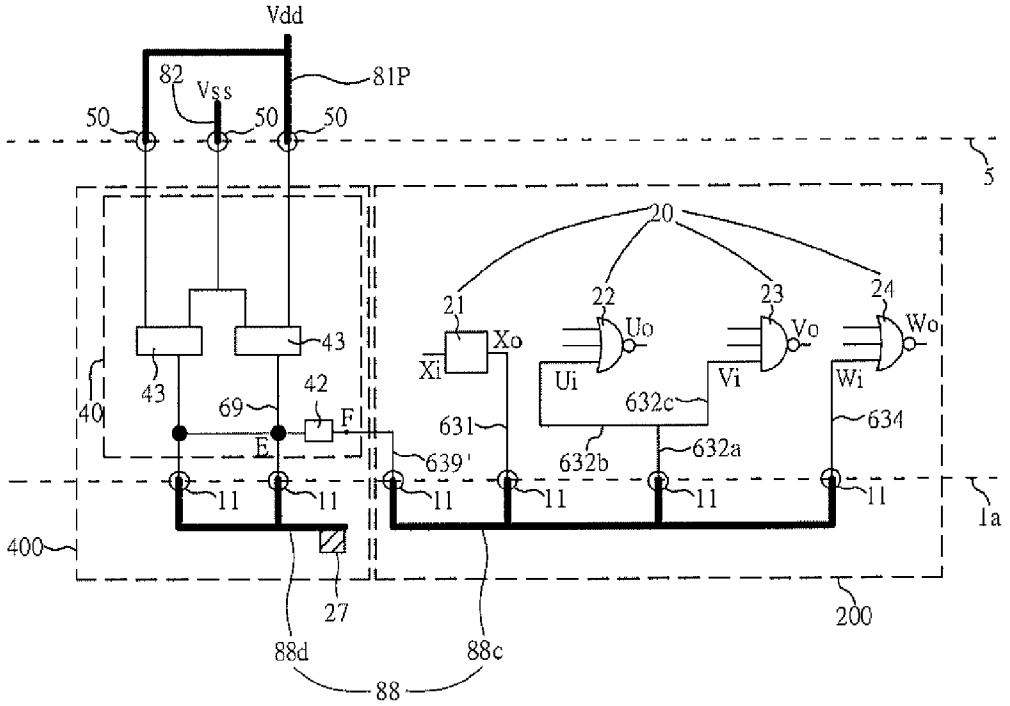


Fig. 29I

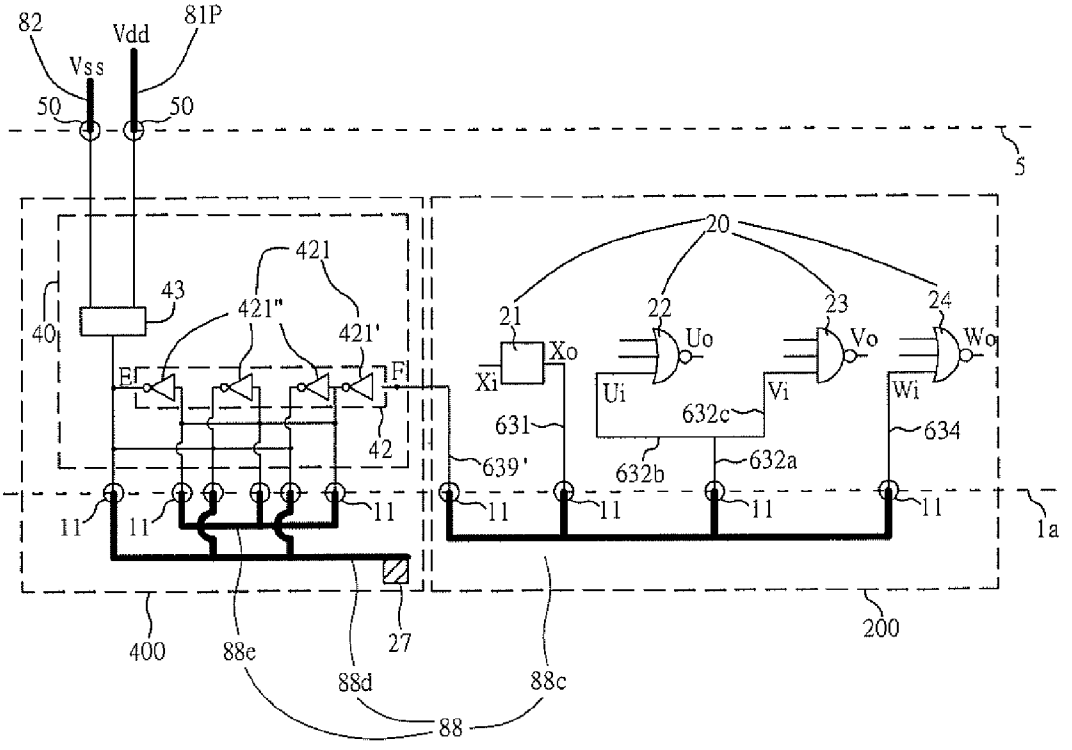


Fig. 29J

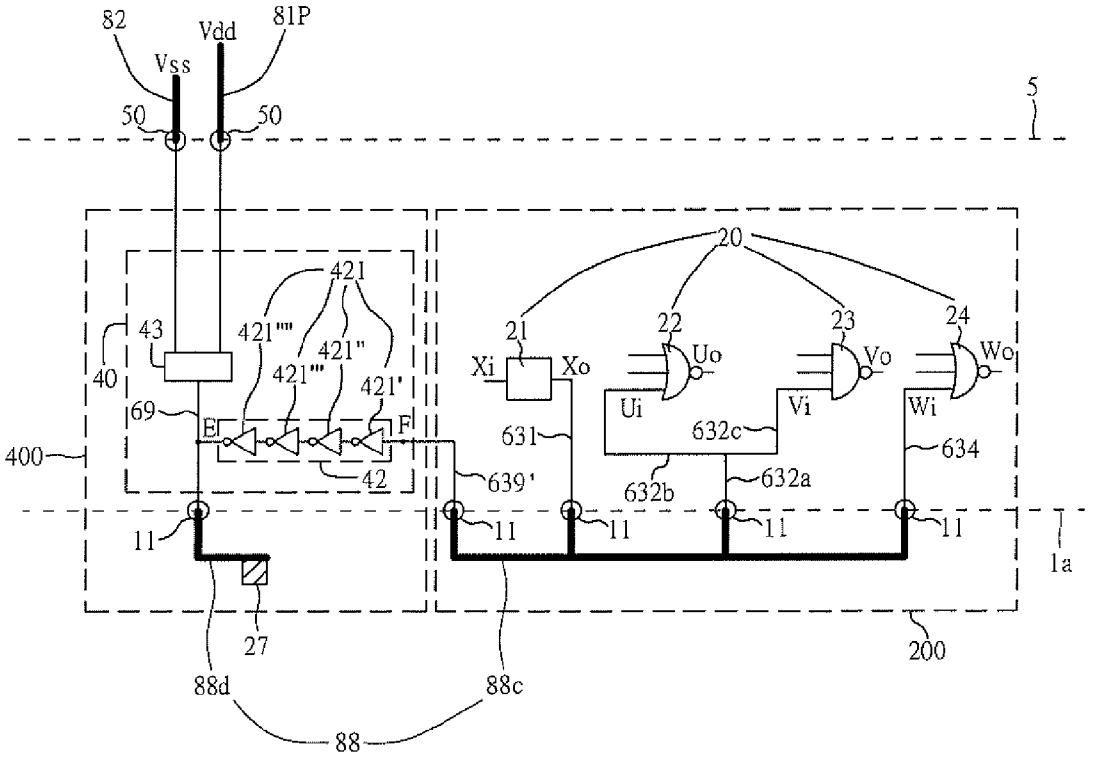


Fig. 29K

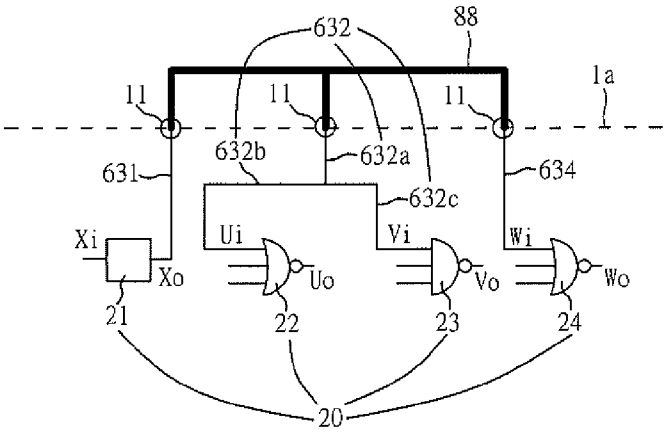


Fig. 29L

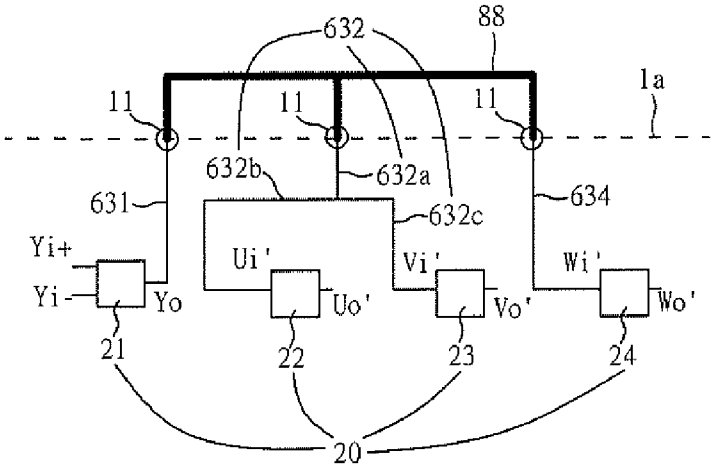


Fig. 29M

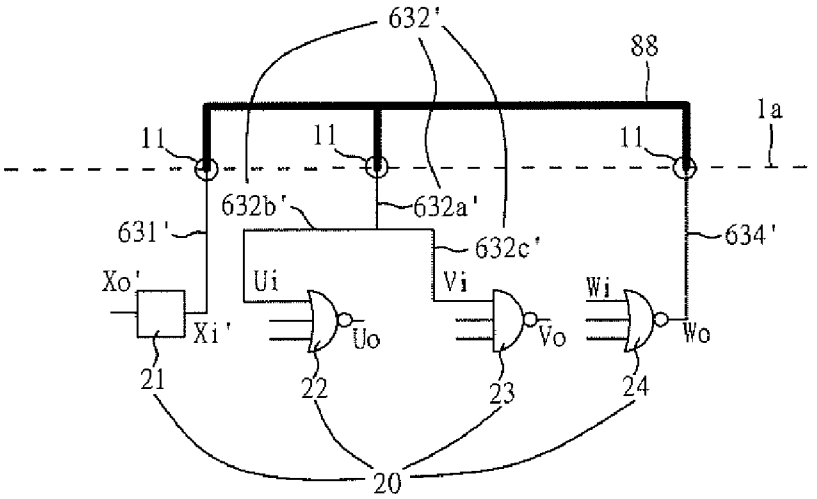


Fig. 29N

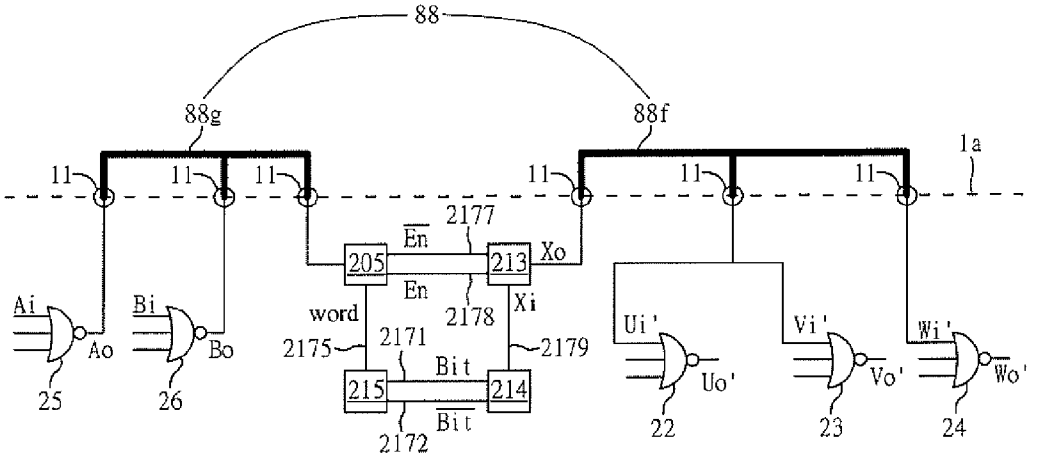


Fig. 29O

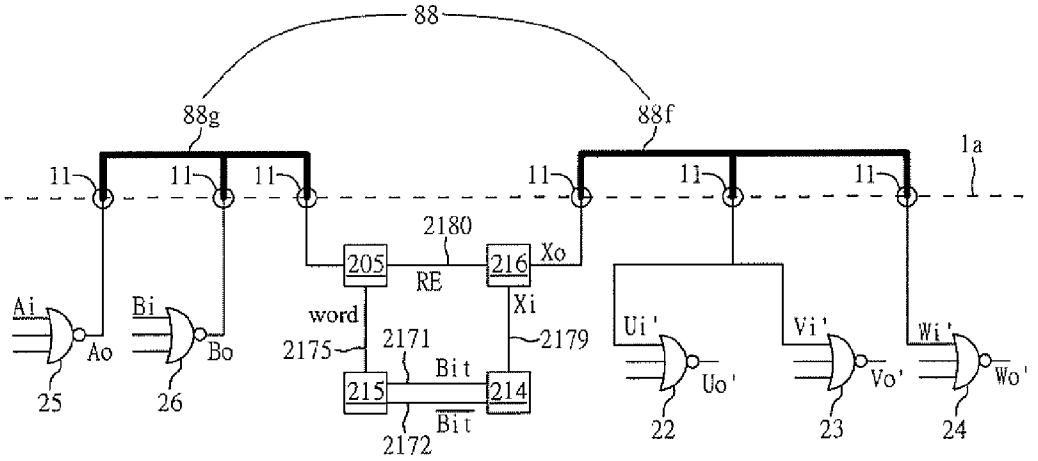


Fig. 29P

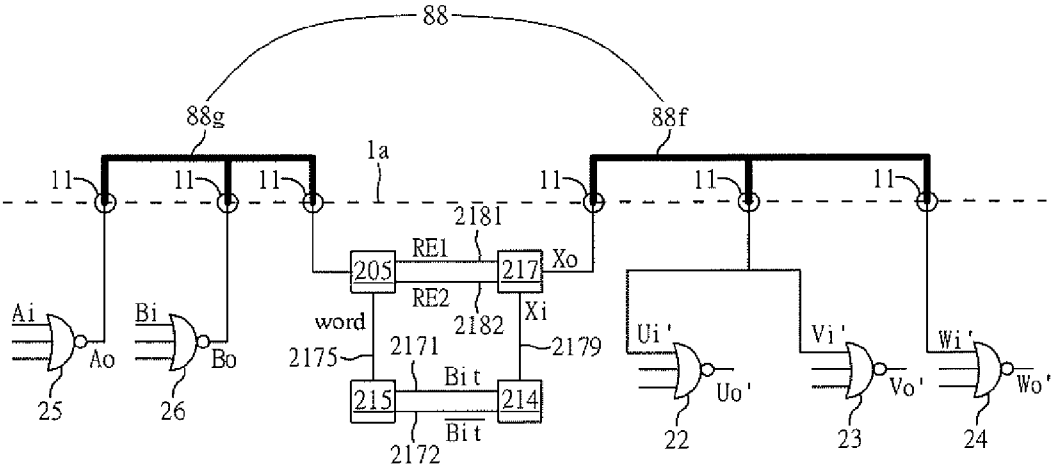


Fig. 29Q

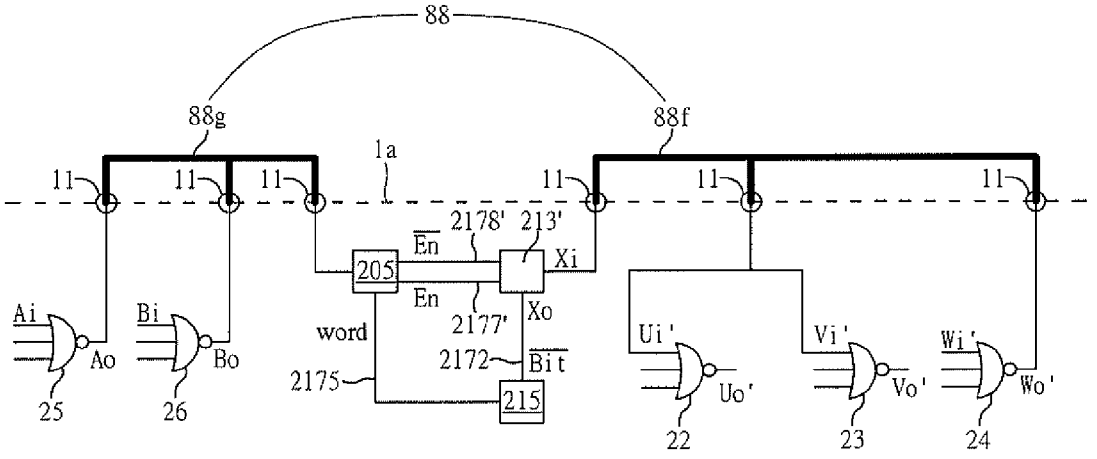


Fig. 29R

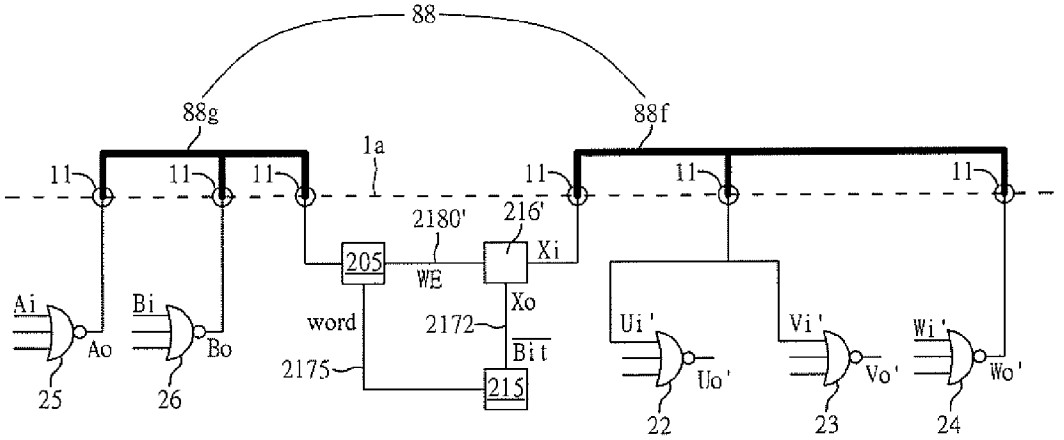


Fig. 29S

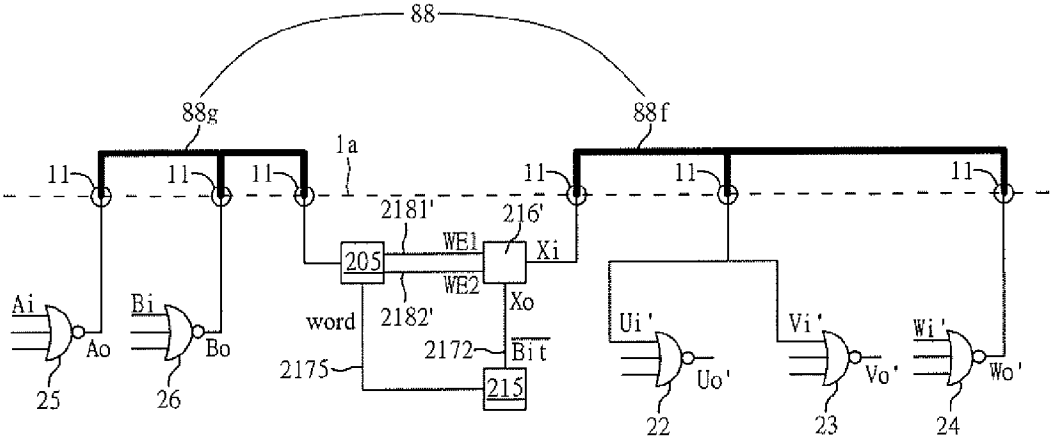


Fig. 29T

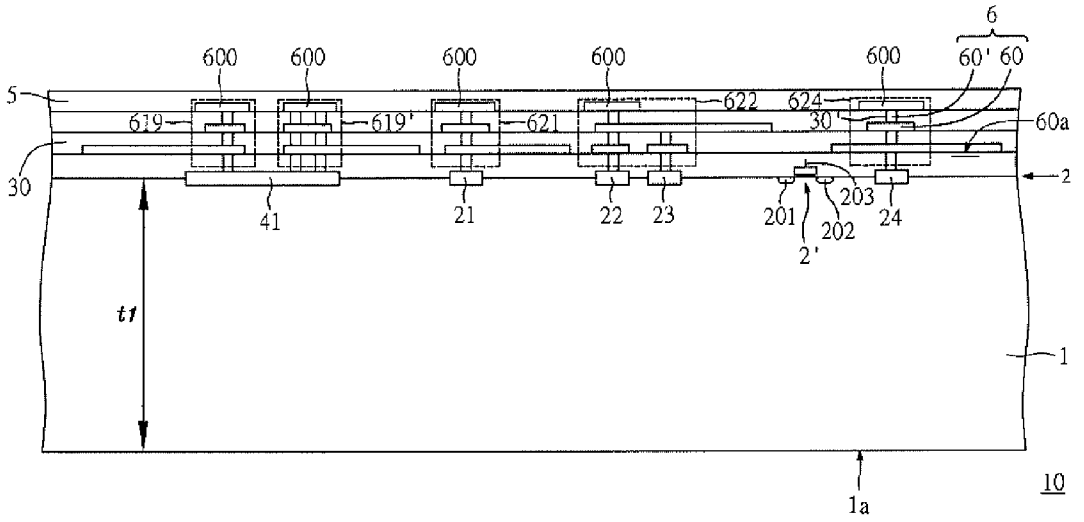


Fig. 30A

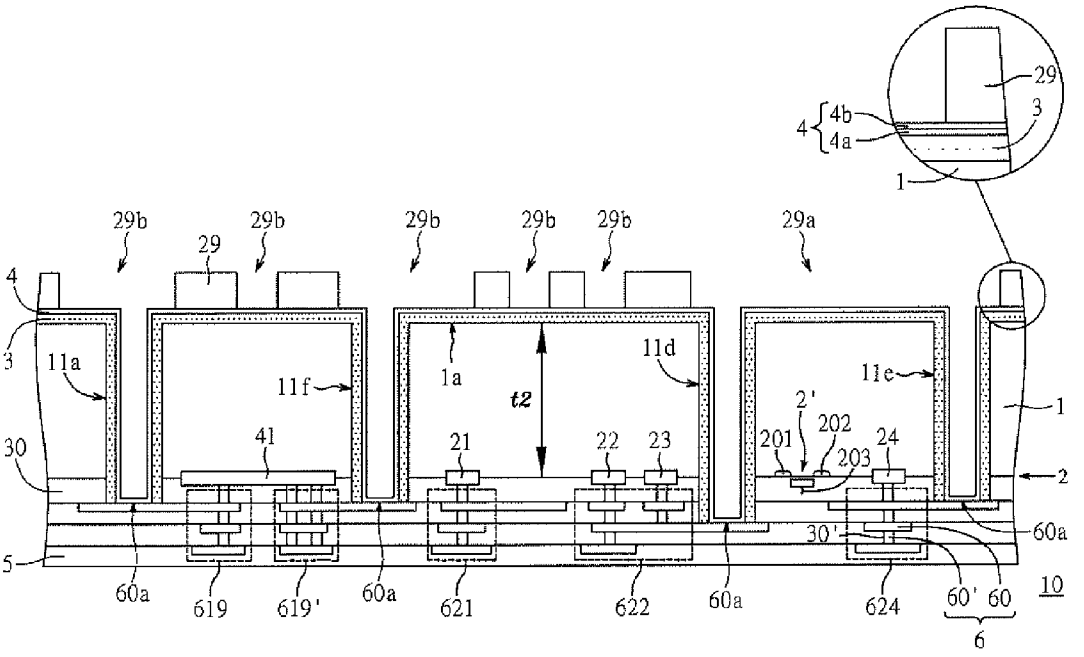


Fig. 30B

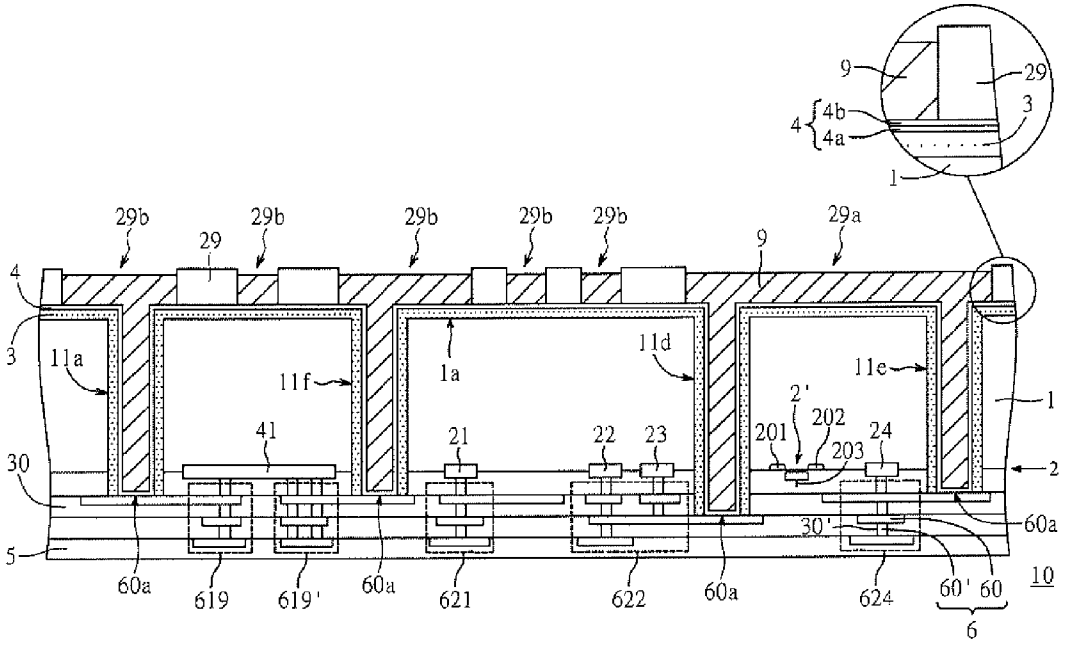


Fig. 30C

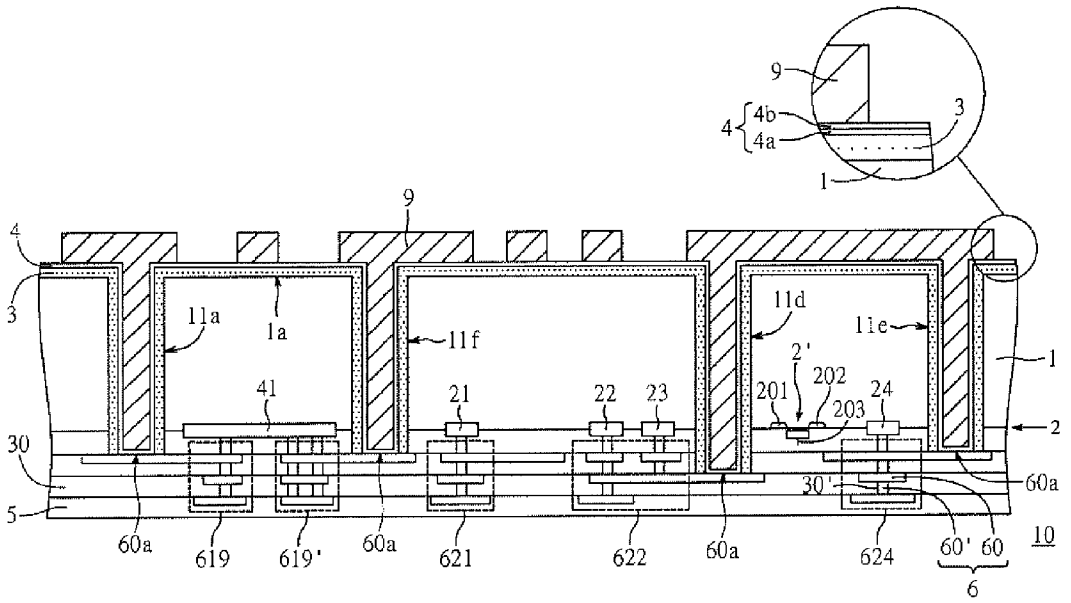


Fig. 30D

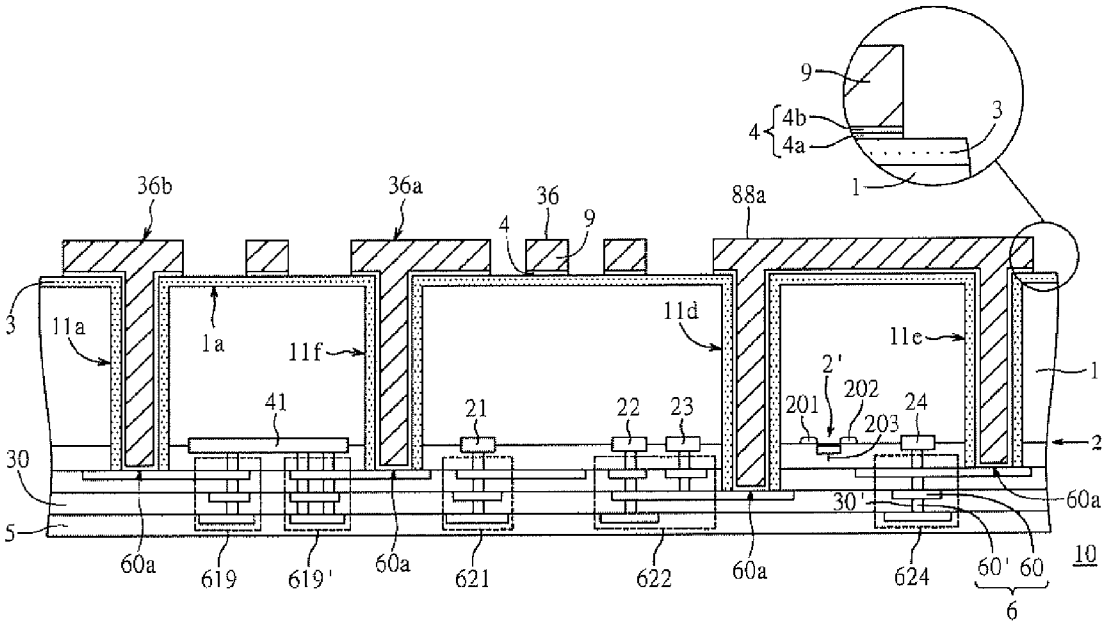


Fig. 30E

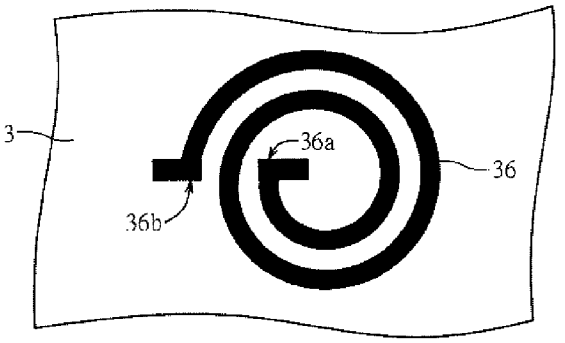


Fig. 30F

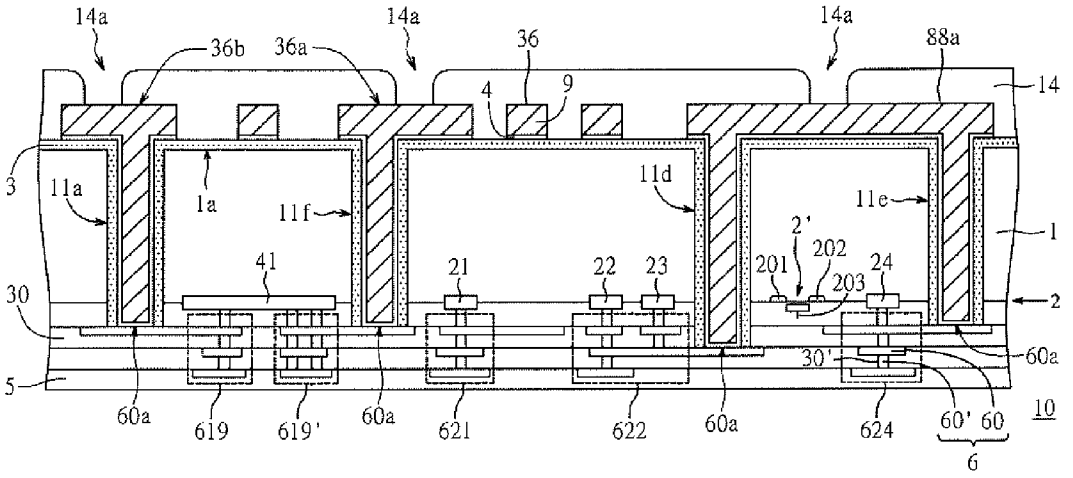


Fig. 30G

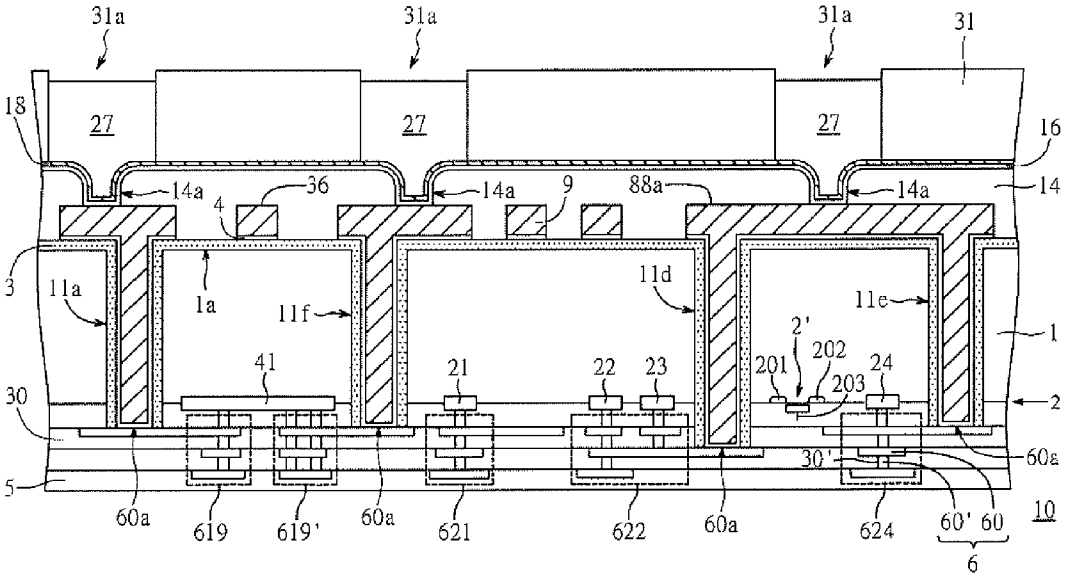


Fig. 30H

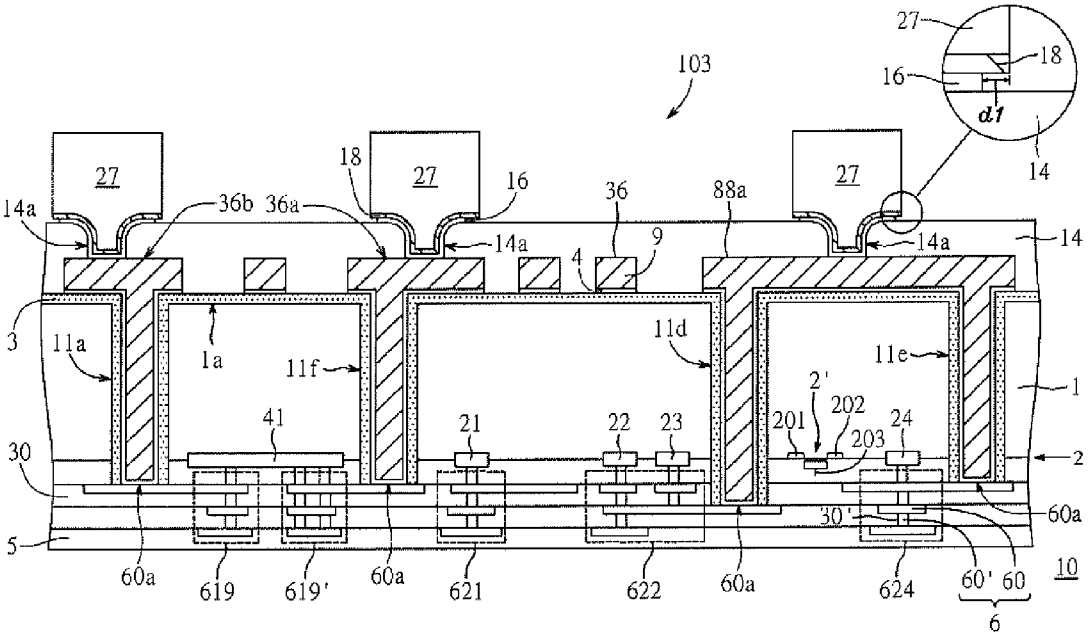


Fig. 30I

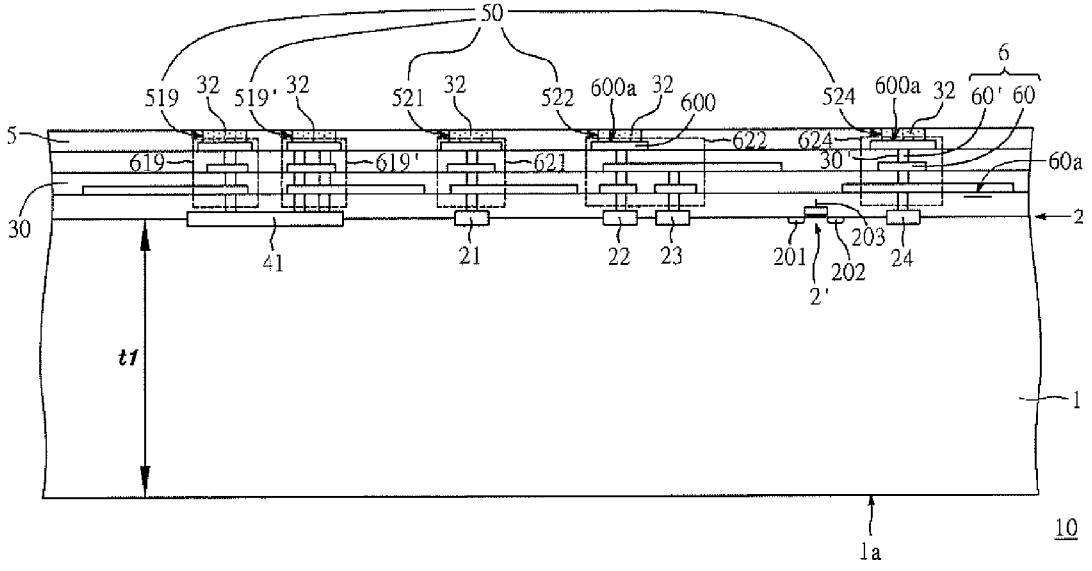


Fig. 30J

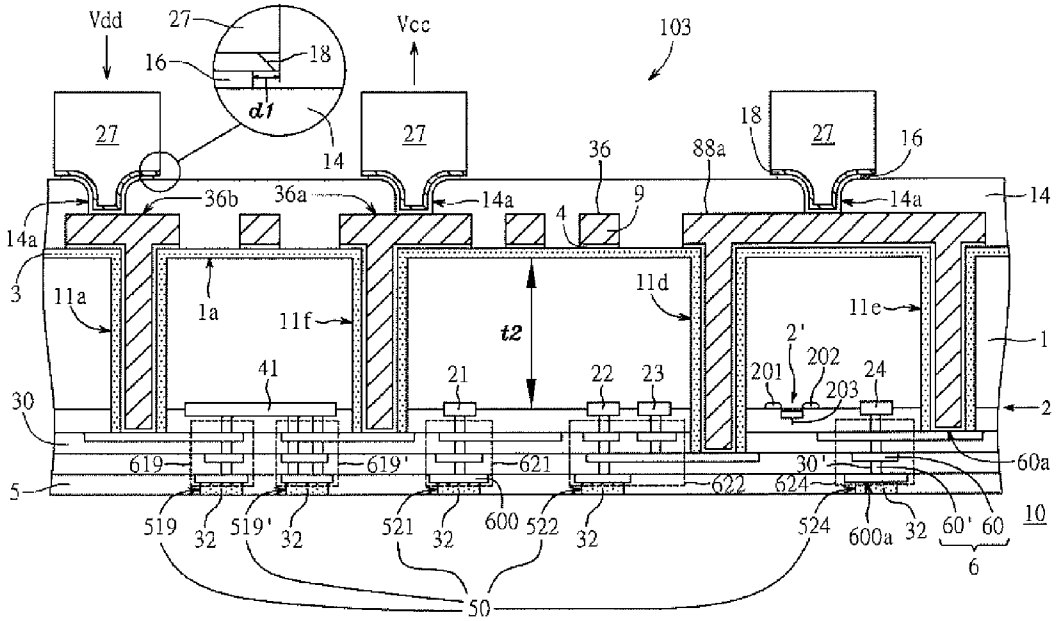


Fig. 30K

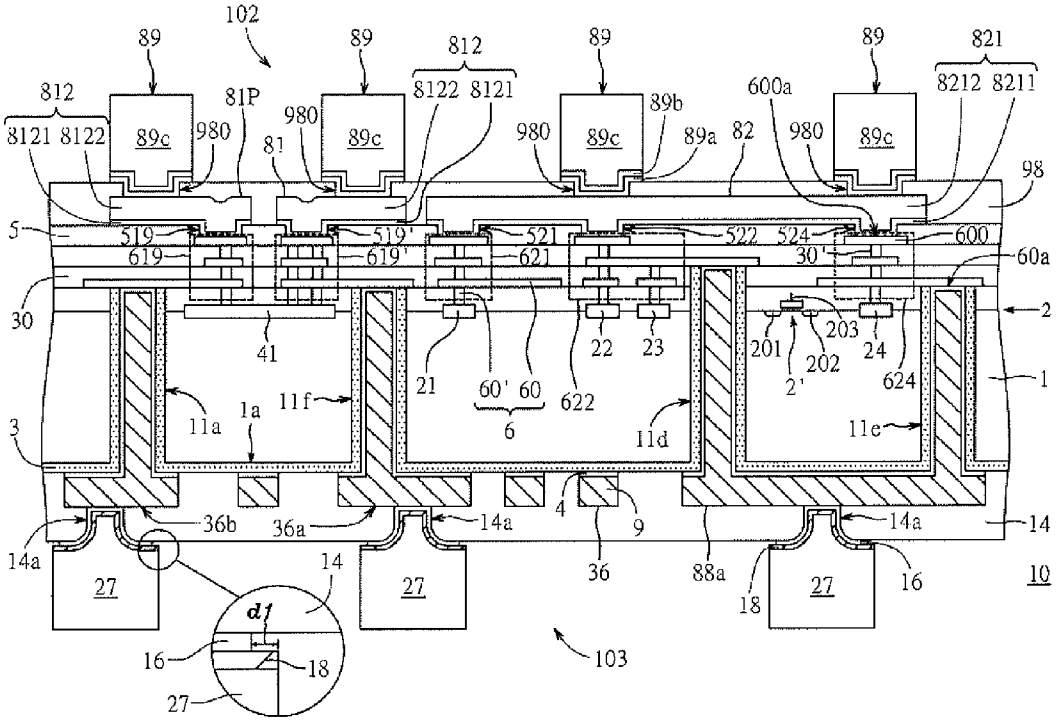


Fig. 30L

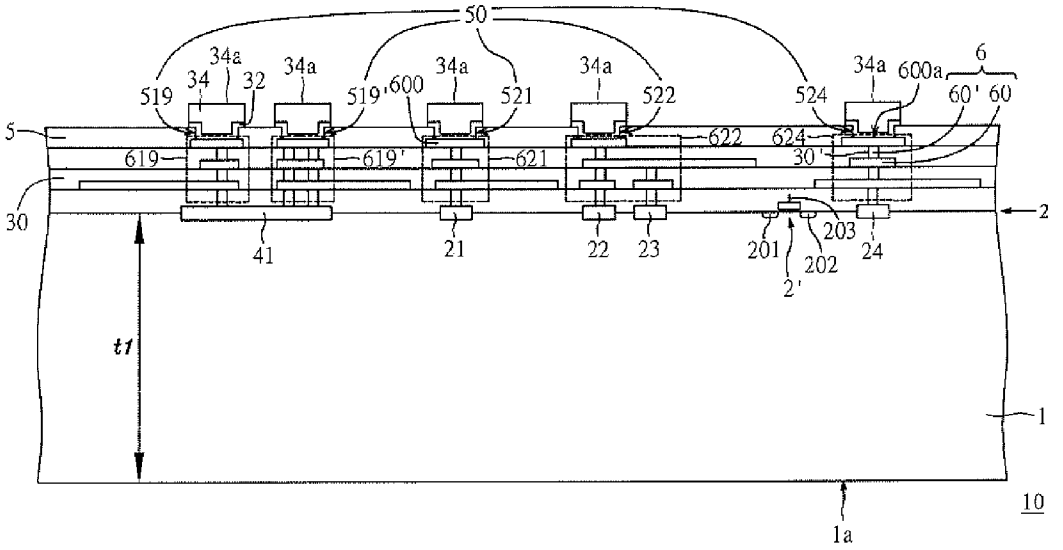


Fig. 30M

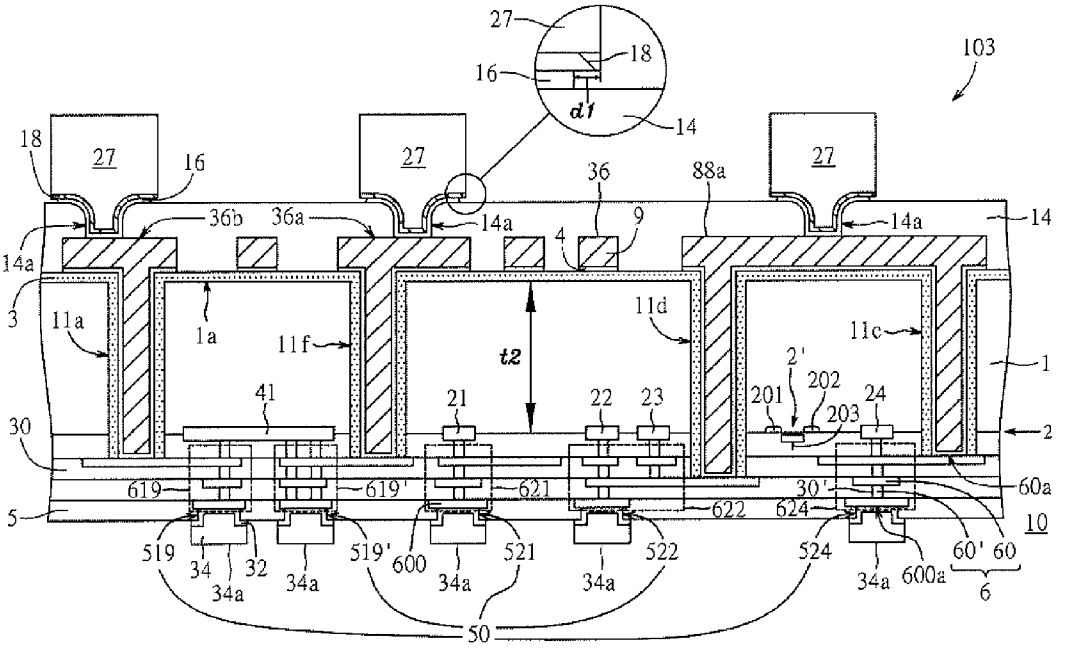


Fig. 30N

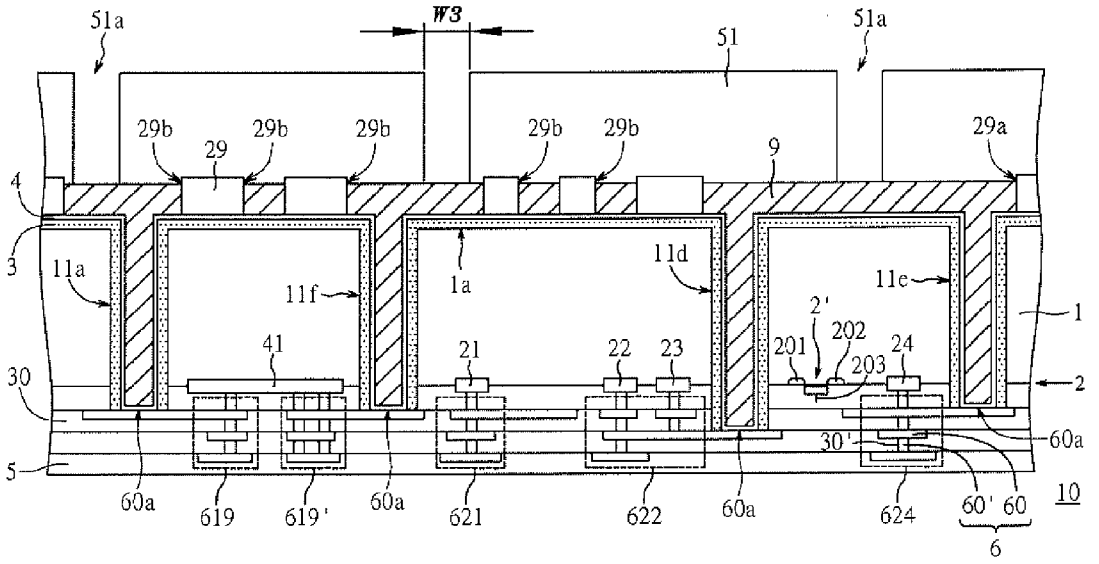


Fig. 31A

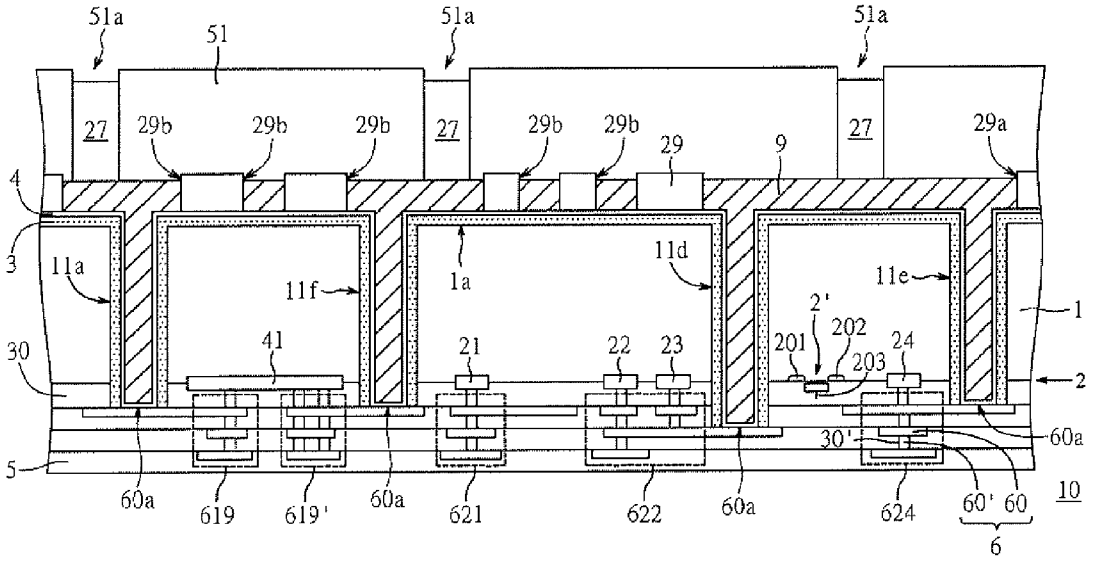


Fig. 31B

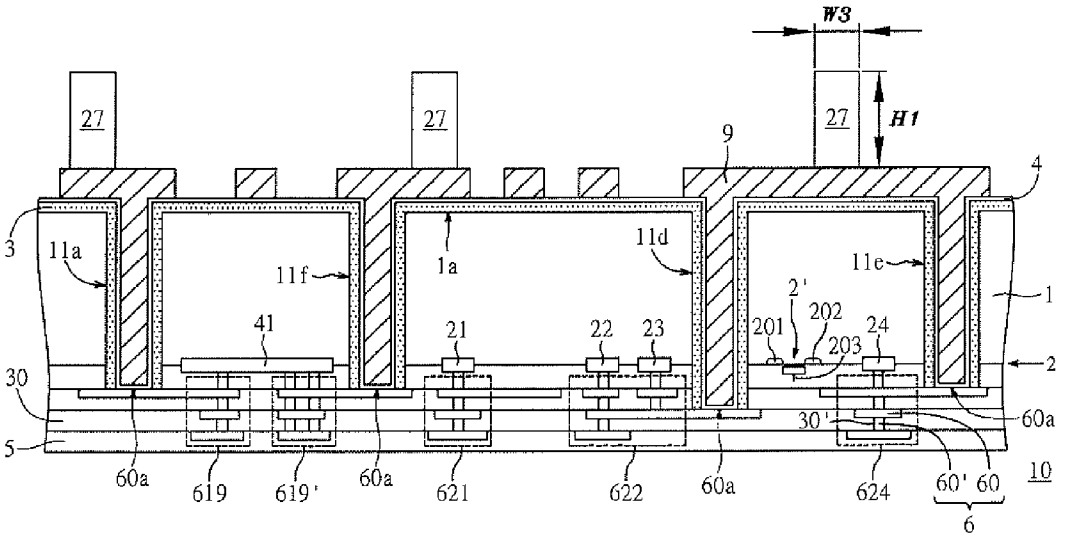


Fig. 31C

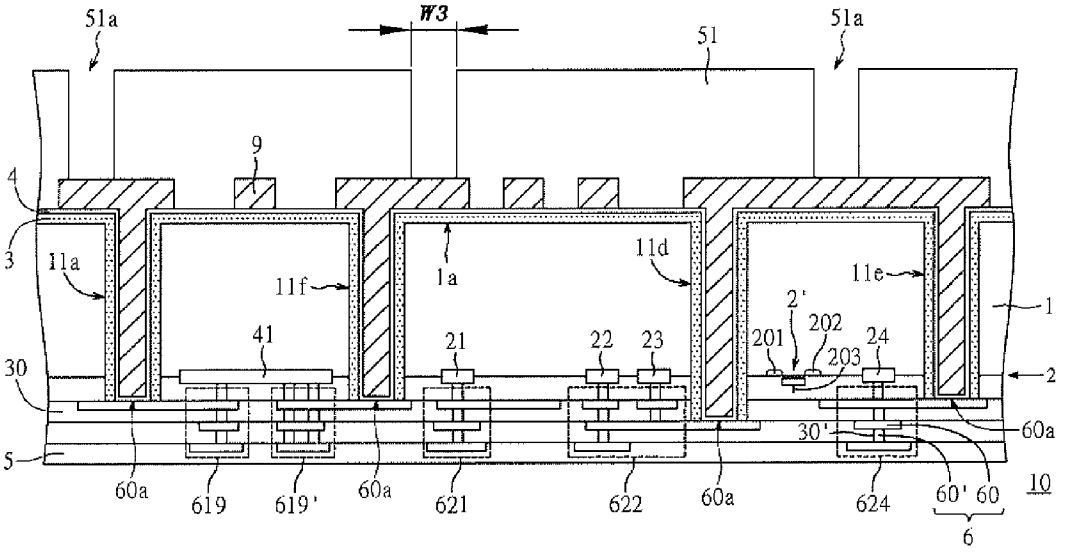


Fig. 31D

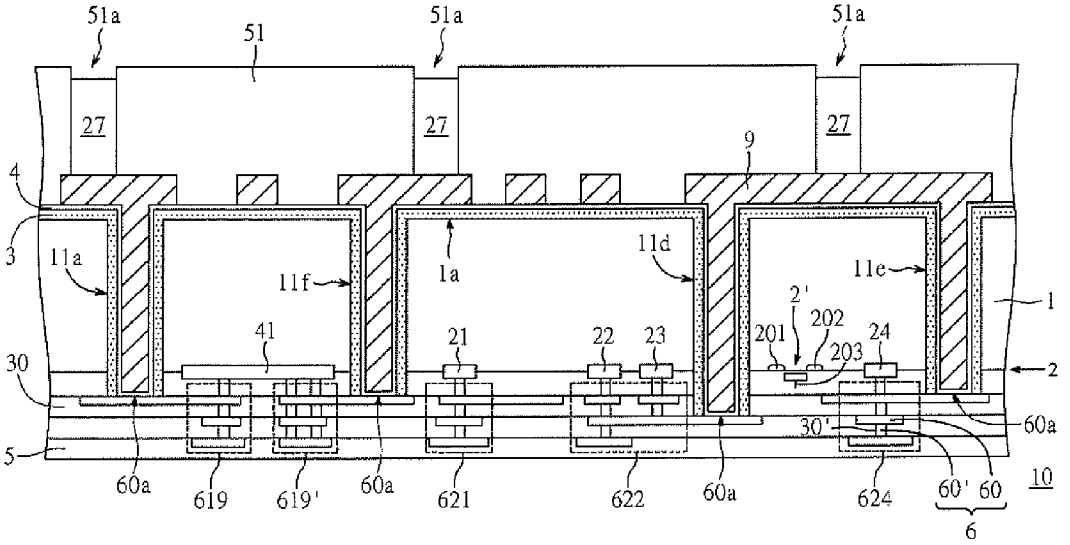


Fig. 31E

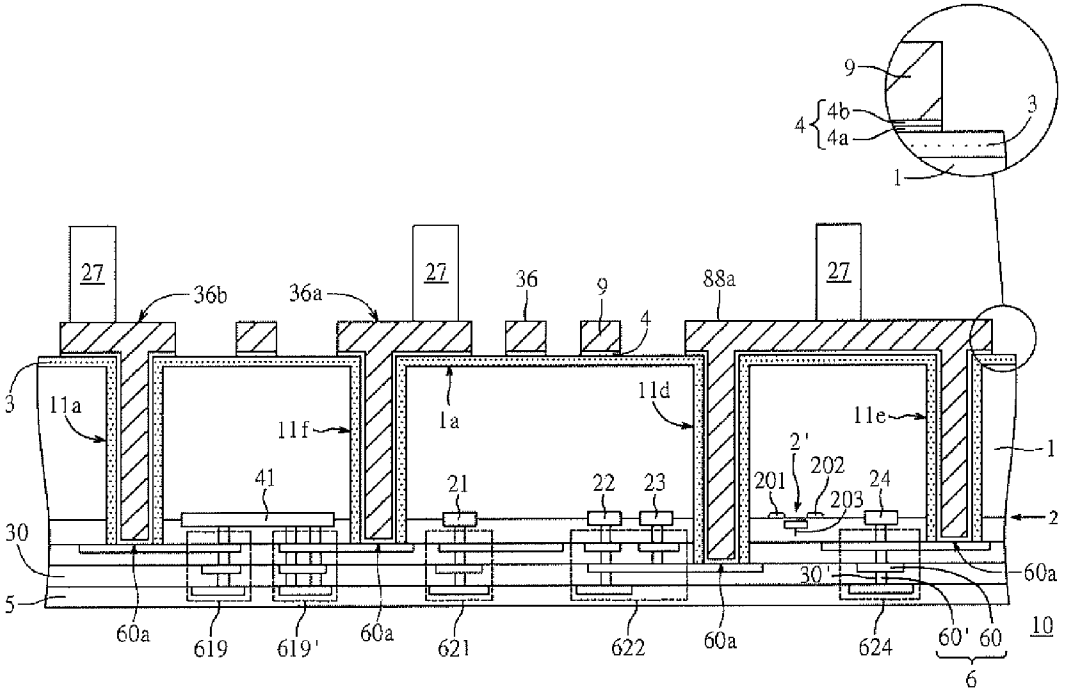


Fig. 31F

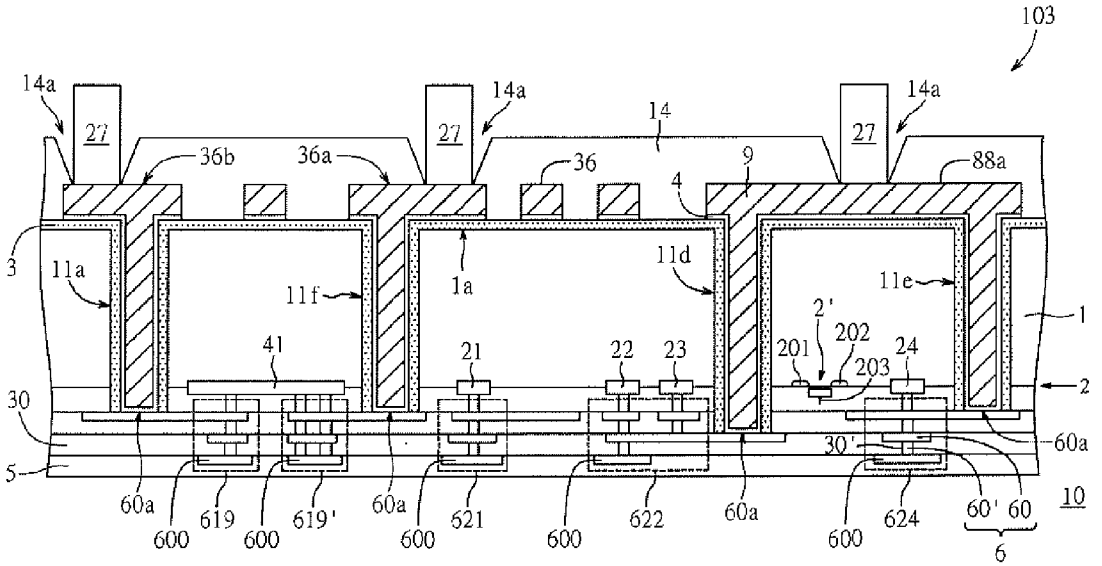


Fig. 31G

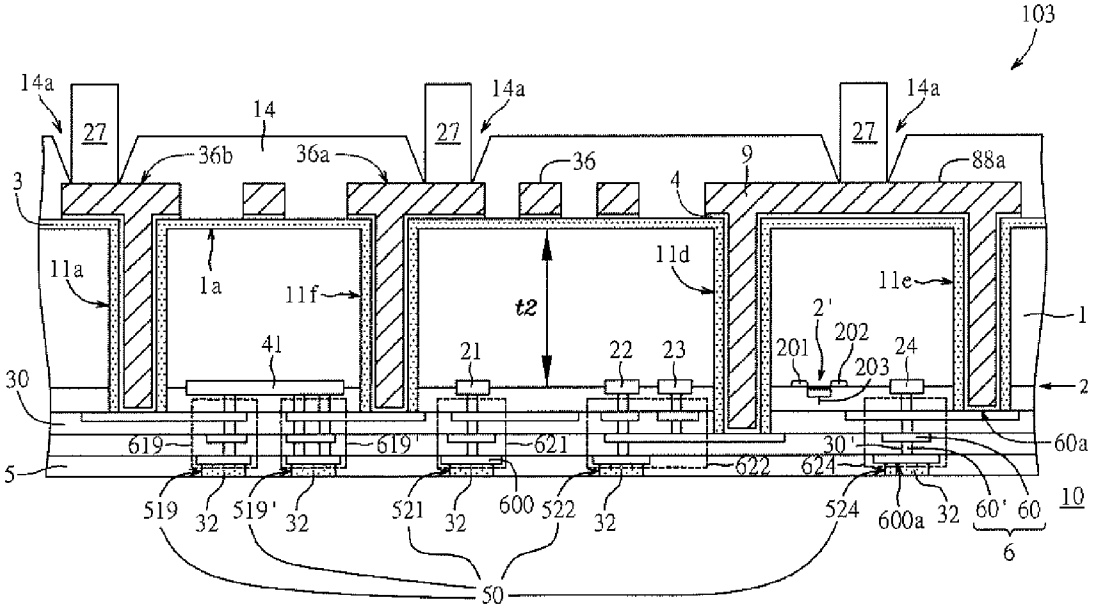


Fig. 31H

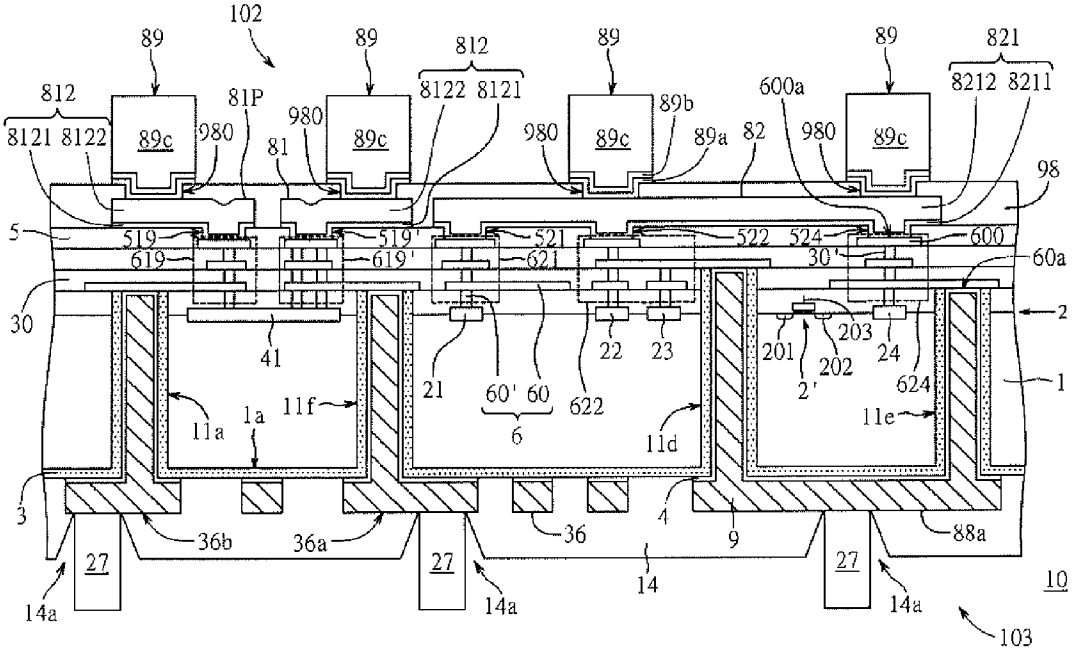


Fig. 31I

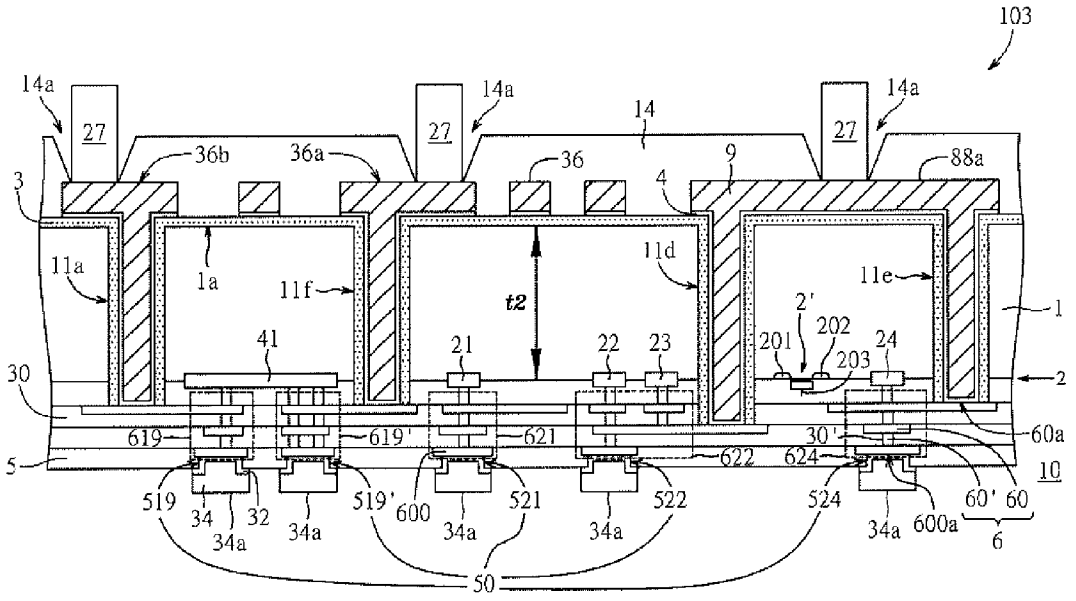


Fig. 31J

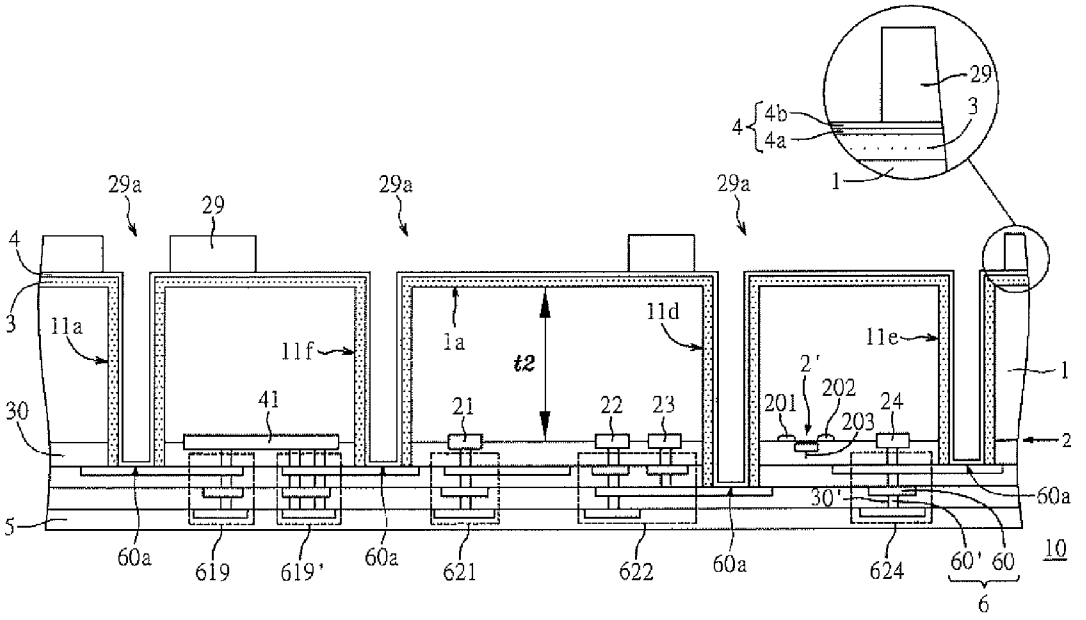


Fig. 32A

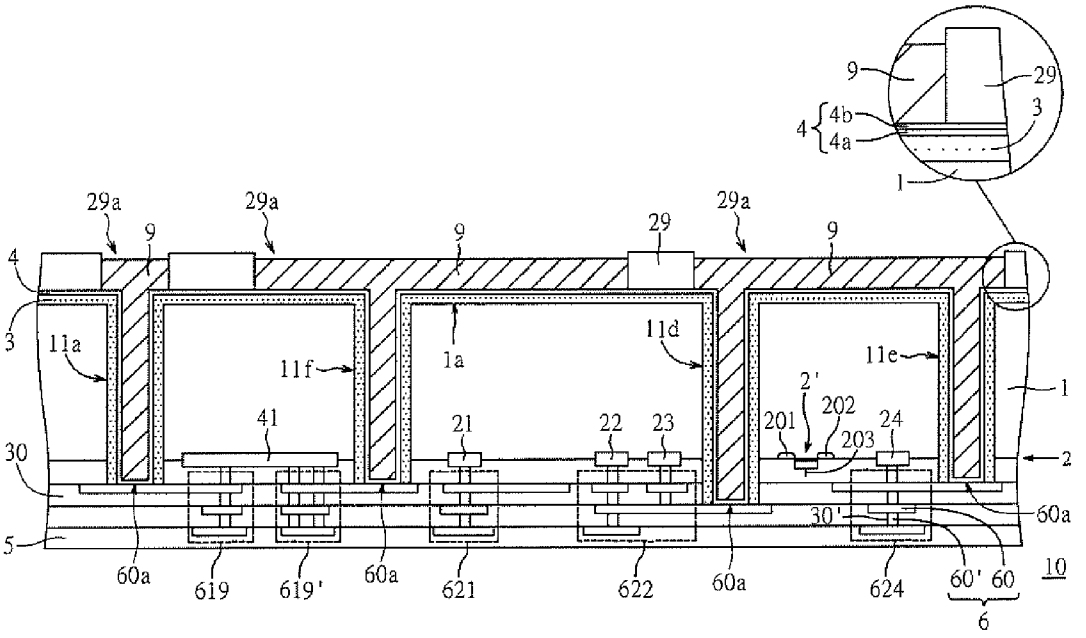


Fig. 32B

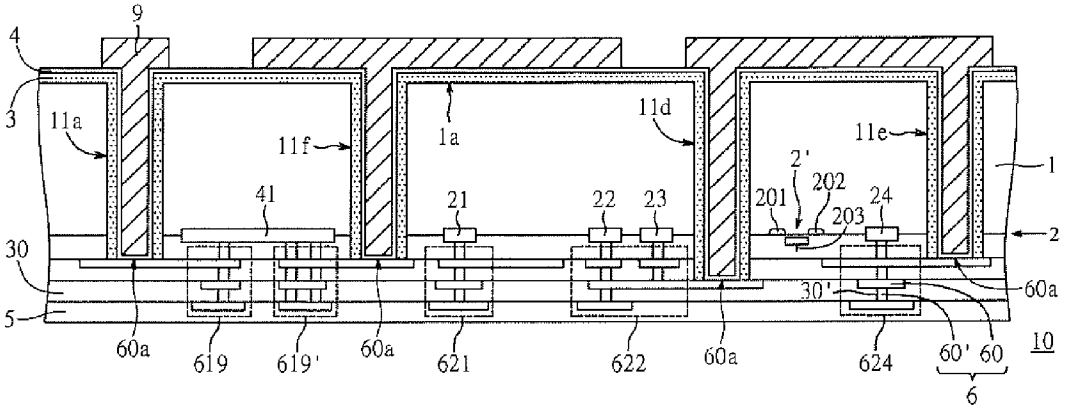


Fig. 32C

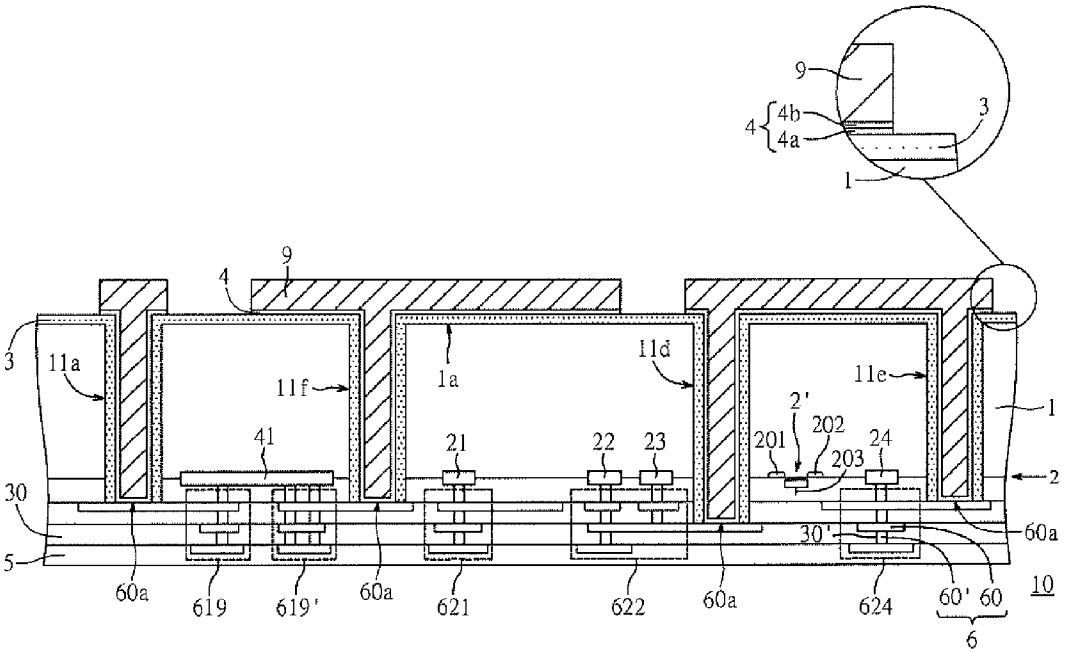


Fig. 32D

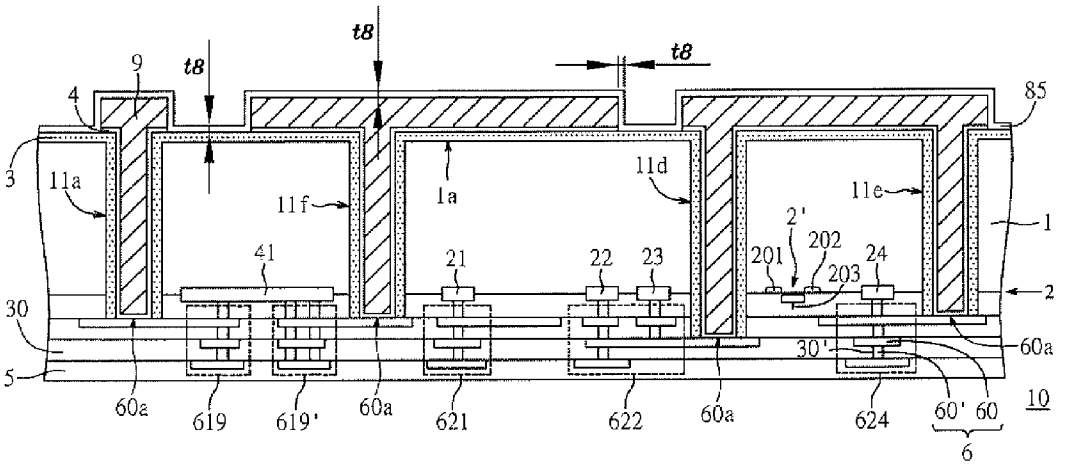


Fig. 32E

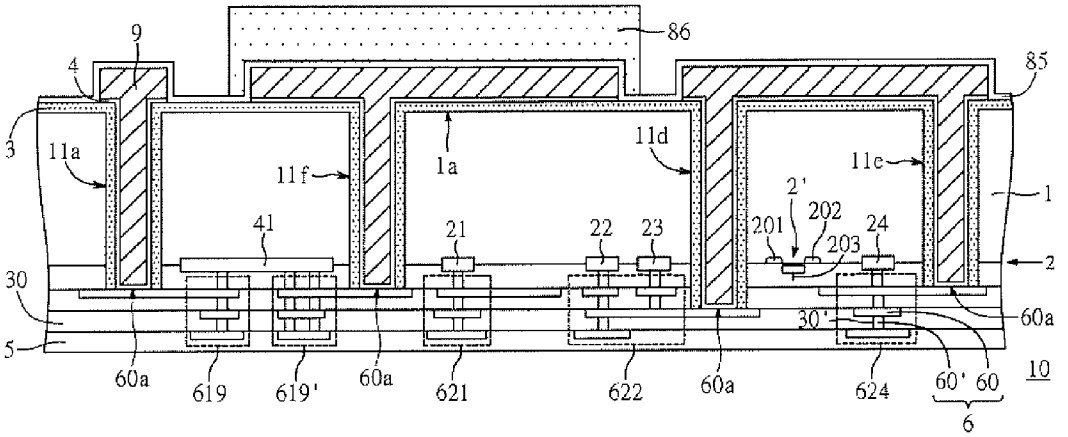


Fig. 32F

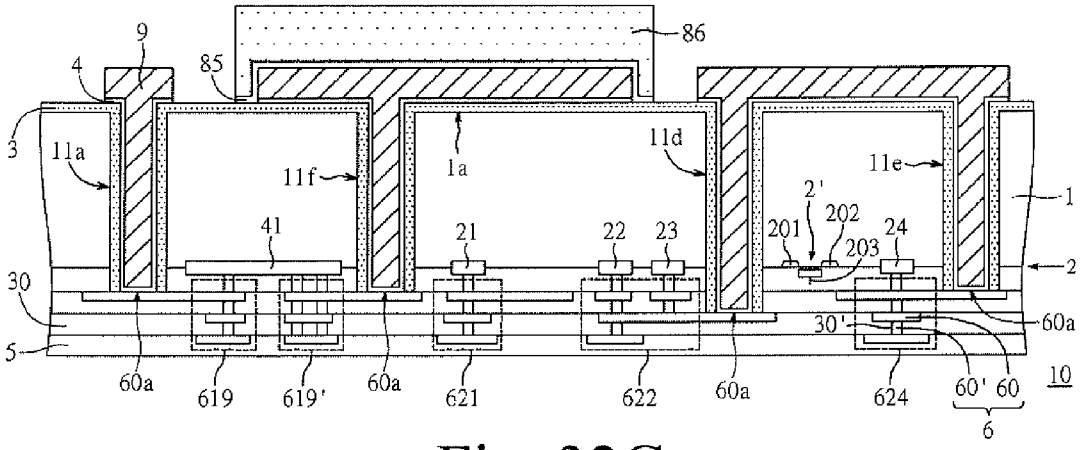


Fig. 32G

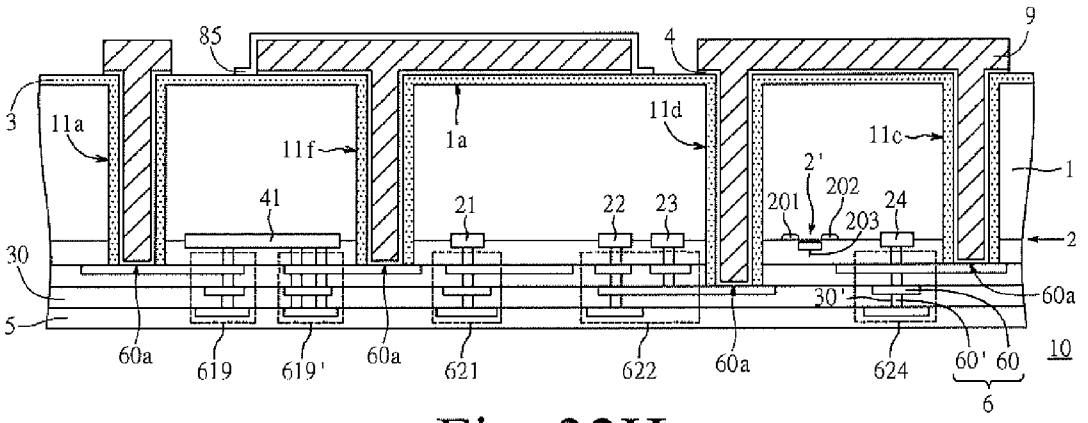


Fig. 32H

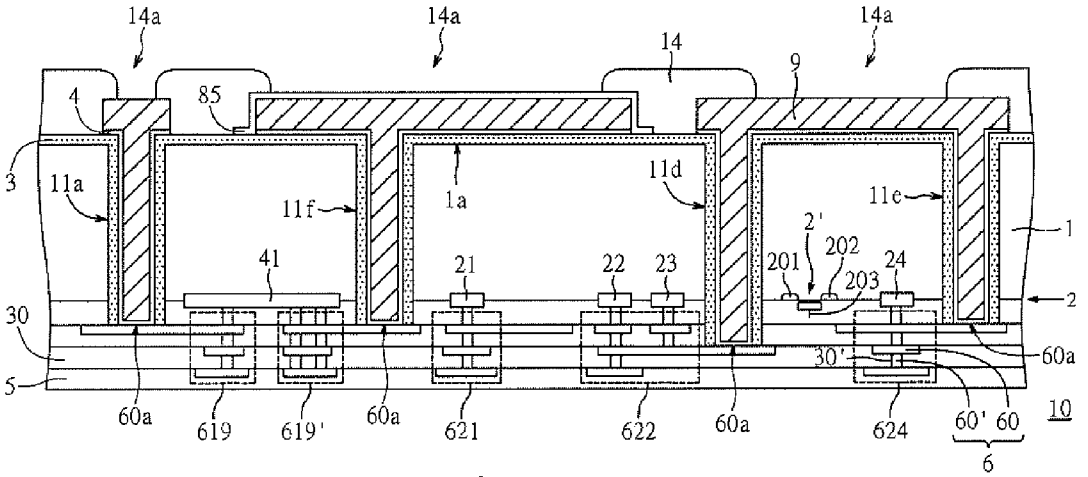


Fig. 32I

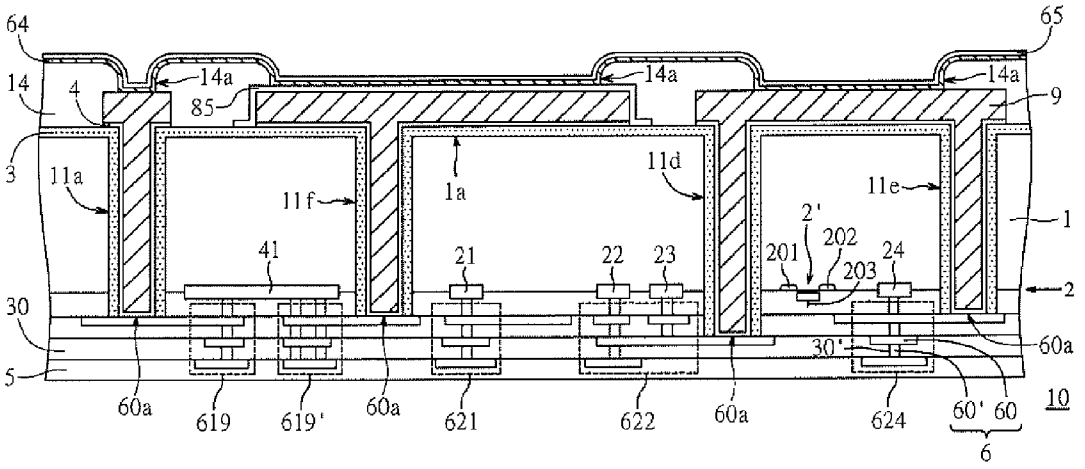


Fig. 32J

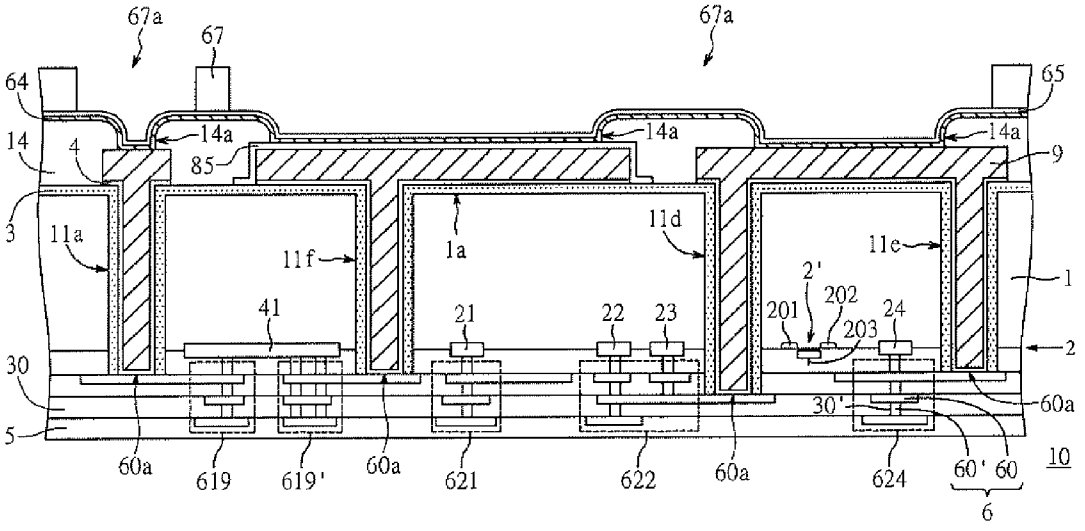


Fig. 32K

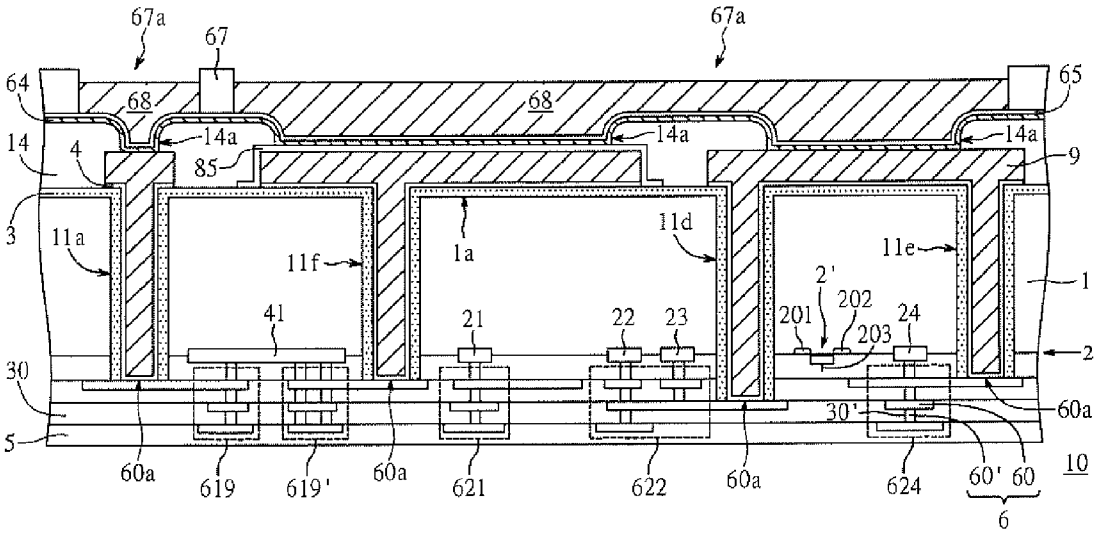


Fig. 32L

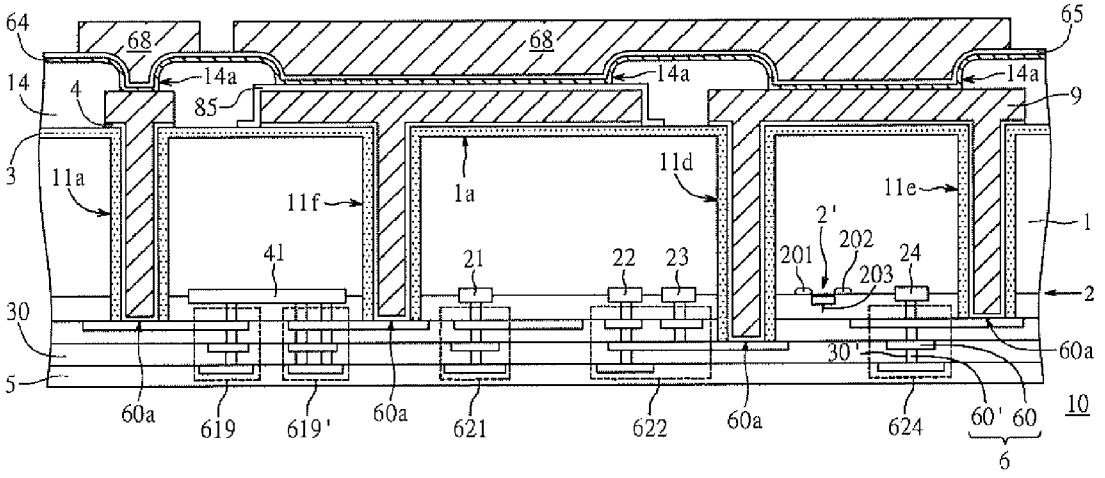


Fig. 32M

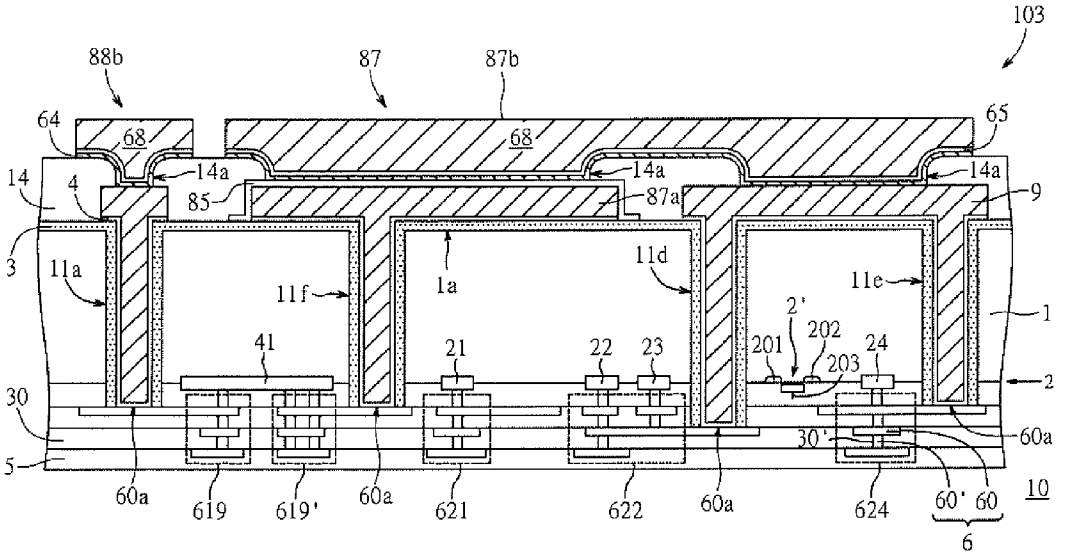


Fig. 32N

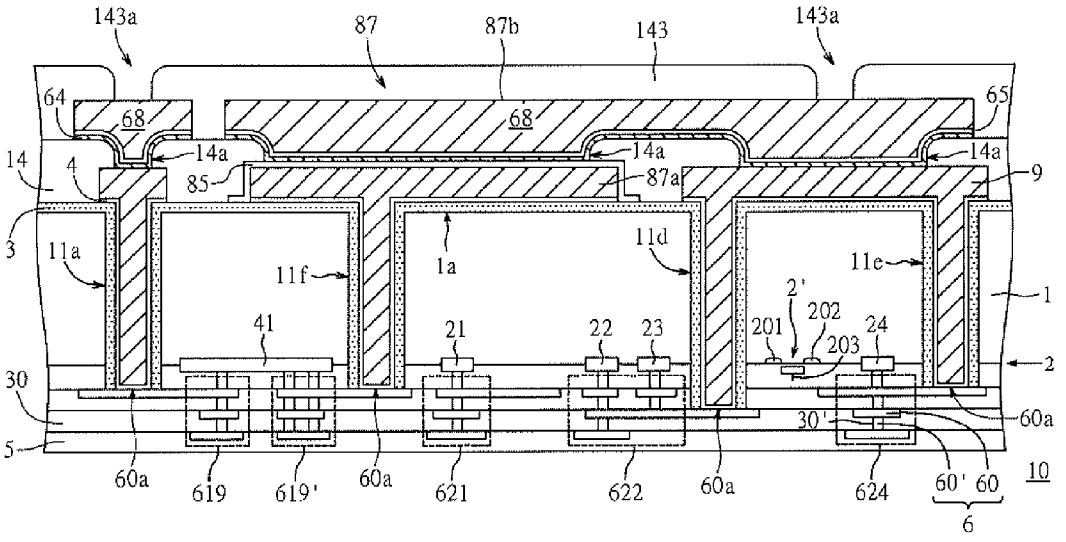


Fig. 32O

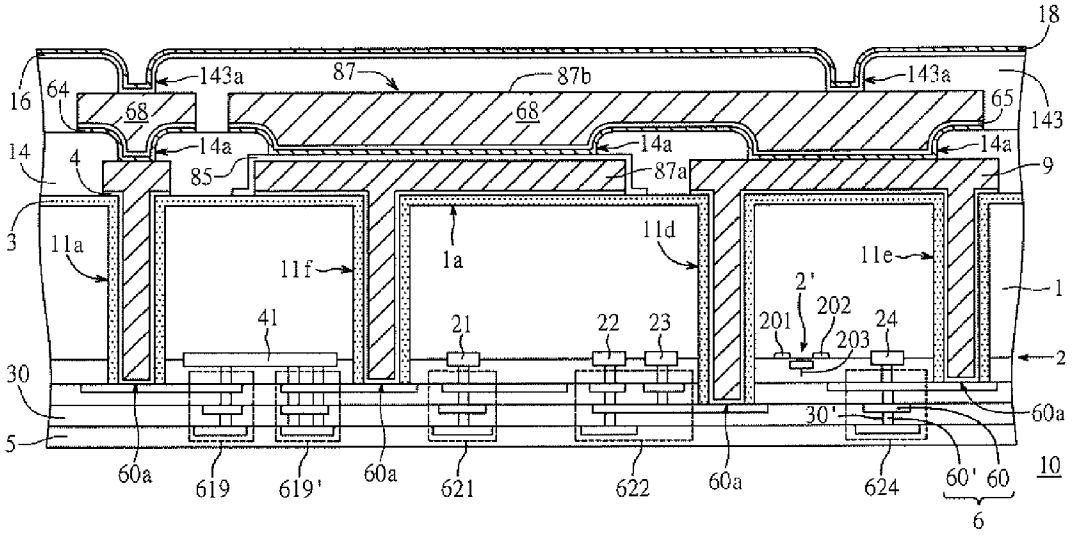


Fig. 32P

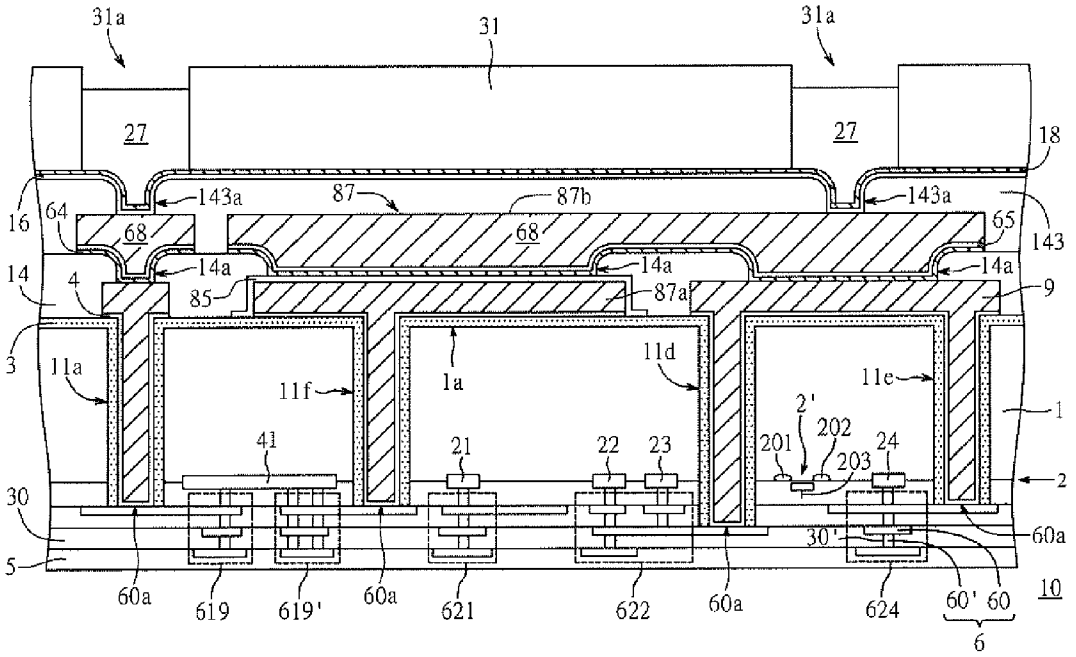


Fig. 32Q

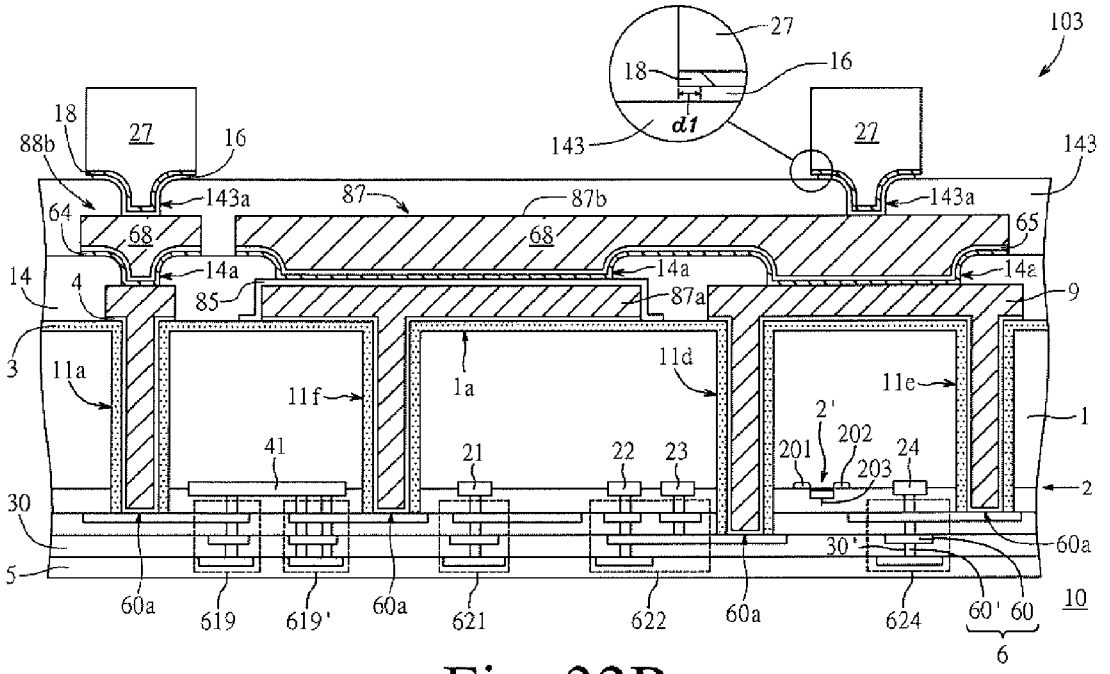


Fig. 32R

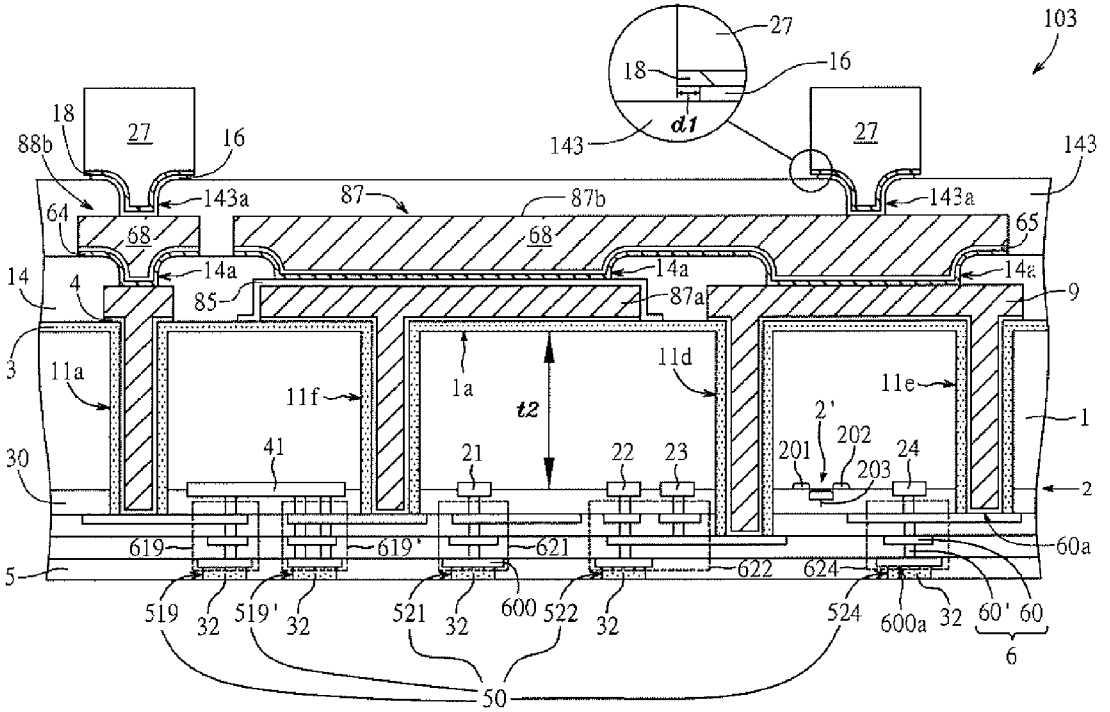


Fig. 32S

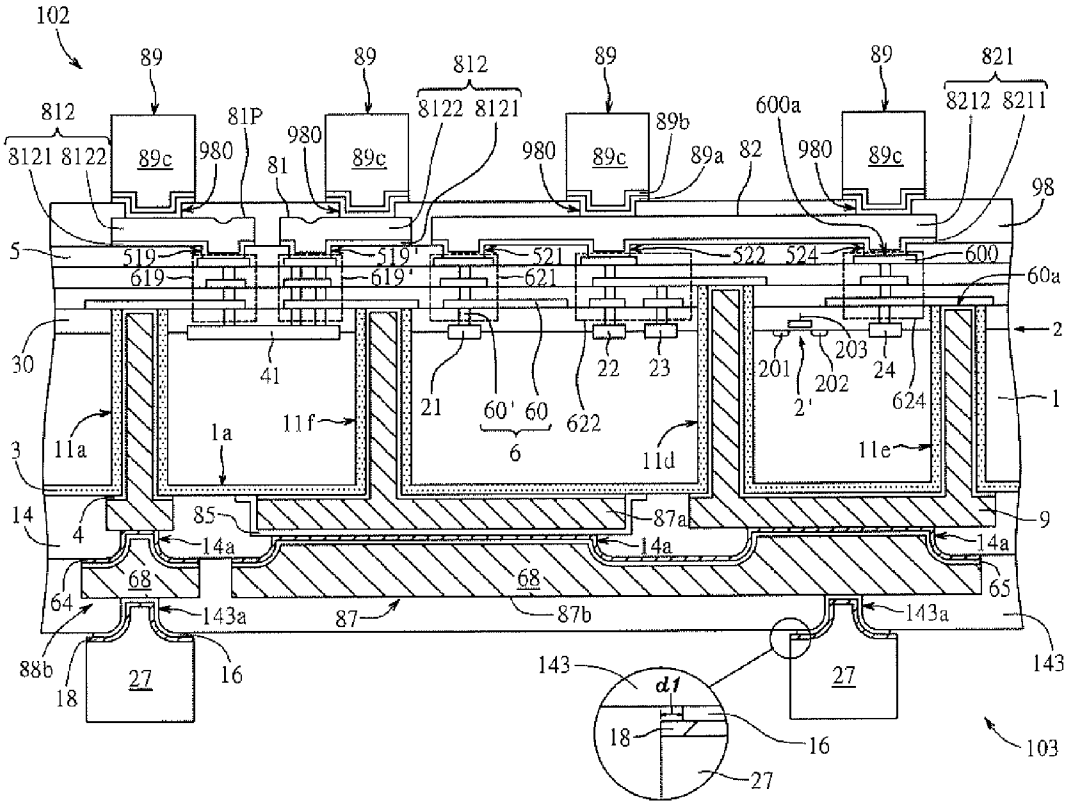

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60a
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60' 60
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2'
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11a
1a
11f
11d
11e
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d1
103

Fig. 32T

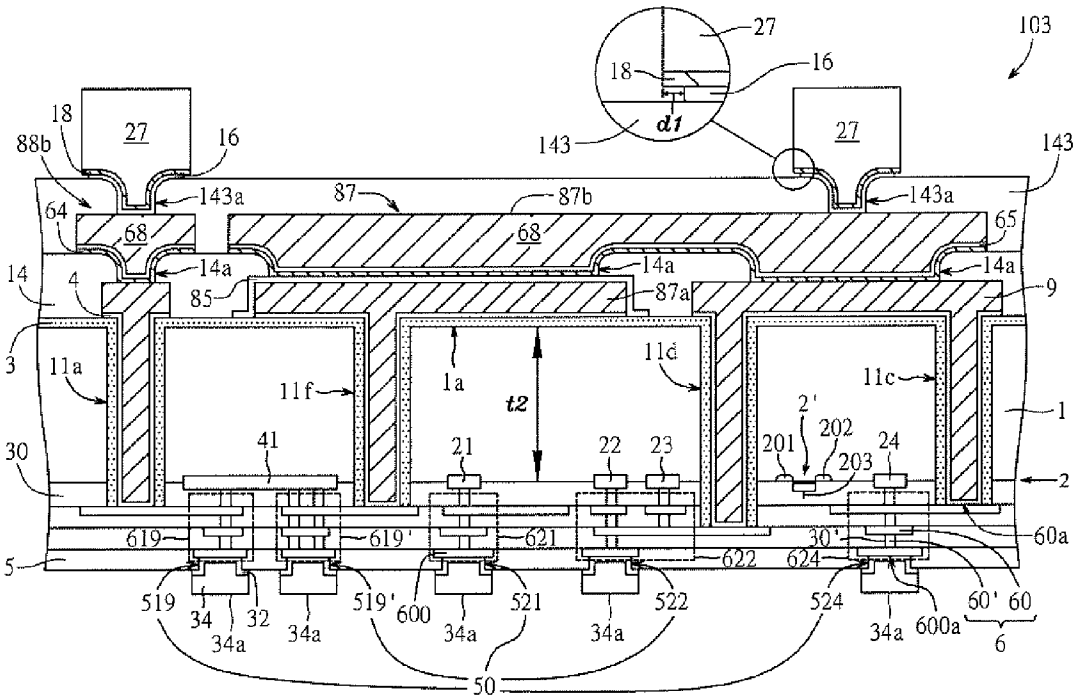

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11d
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87b
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143a
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11c
2'
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203
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619'
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624
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Fig. 32U

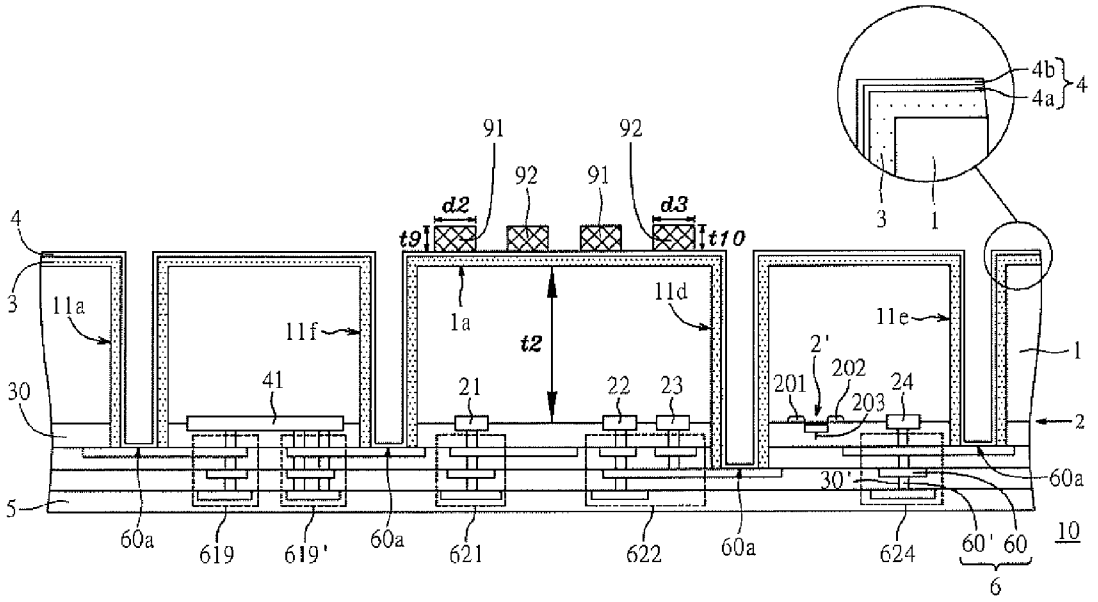


Fig. 33A

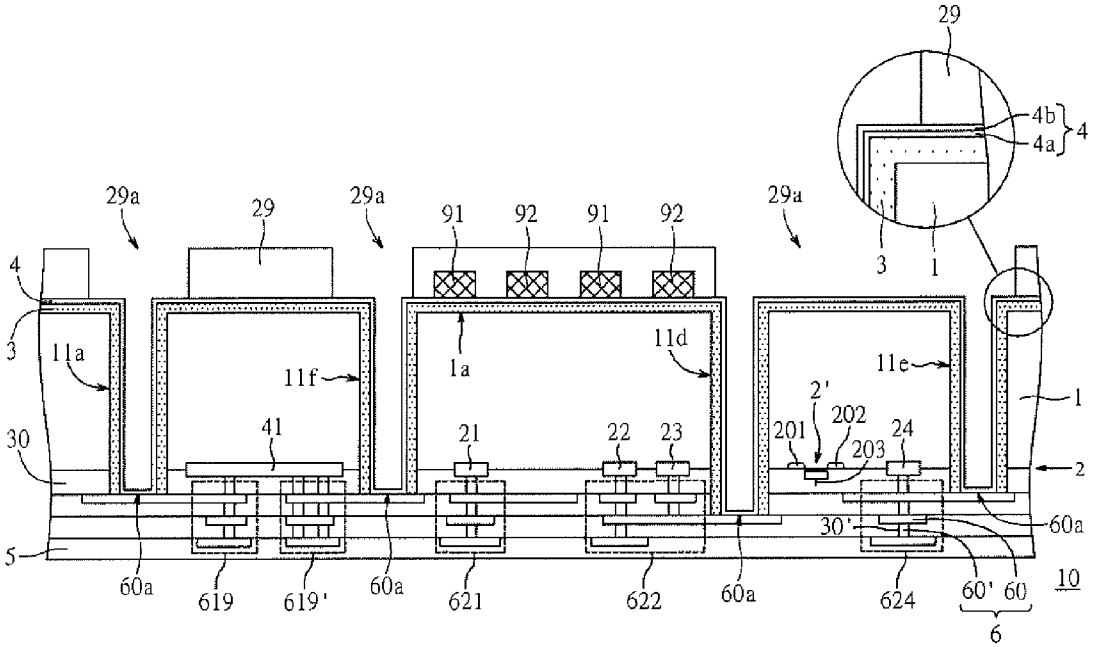


Fig. 33B

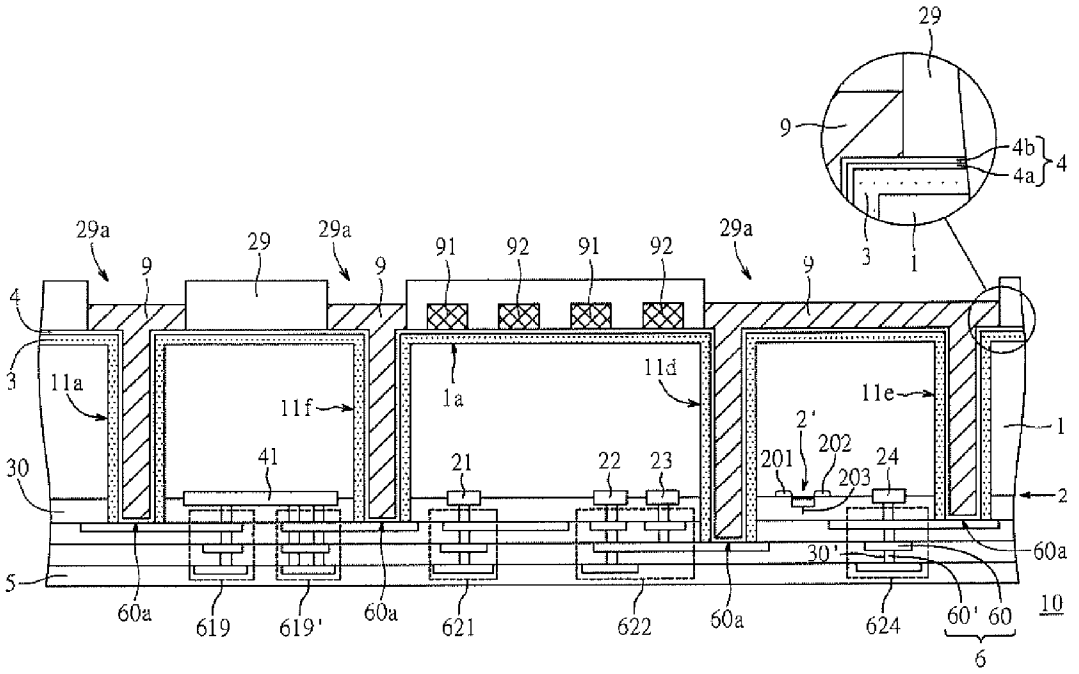


Fig. 33C

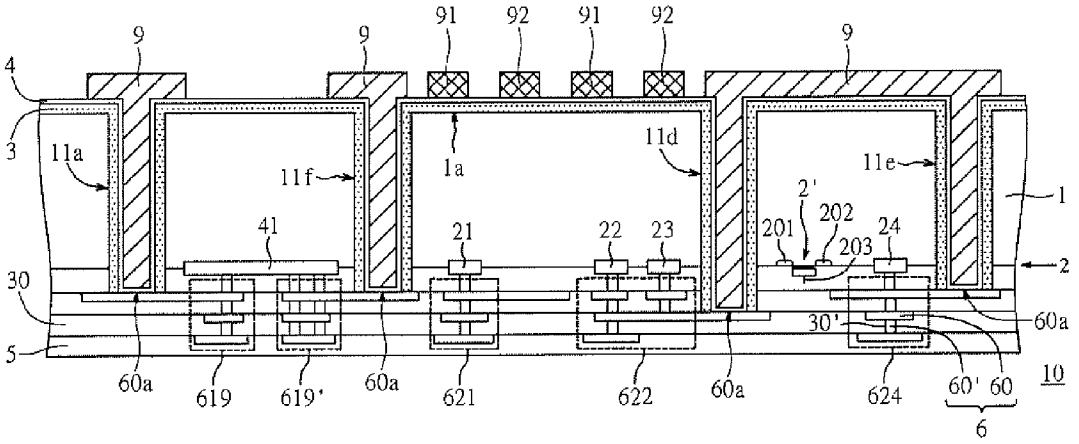


Fig. 33D

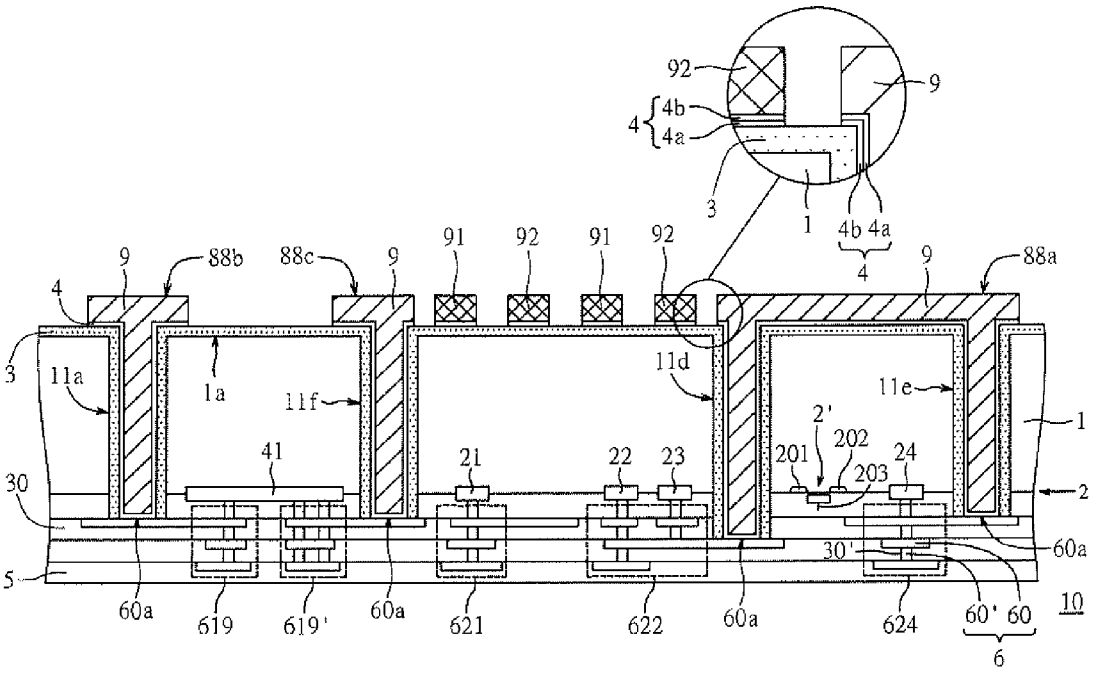


Fig. 33E

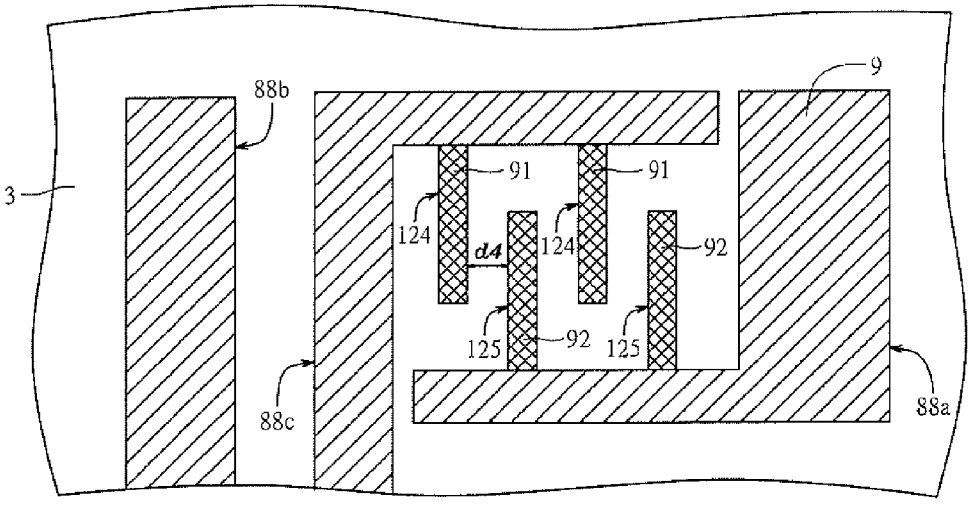


Fig. 33F

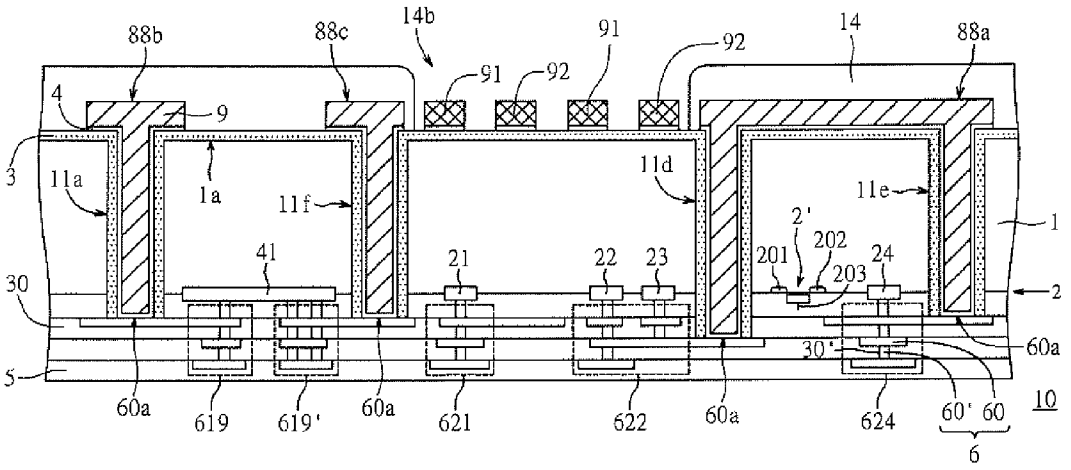


Fig. 33G

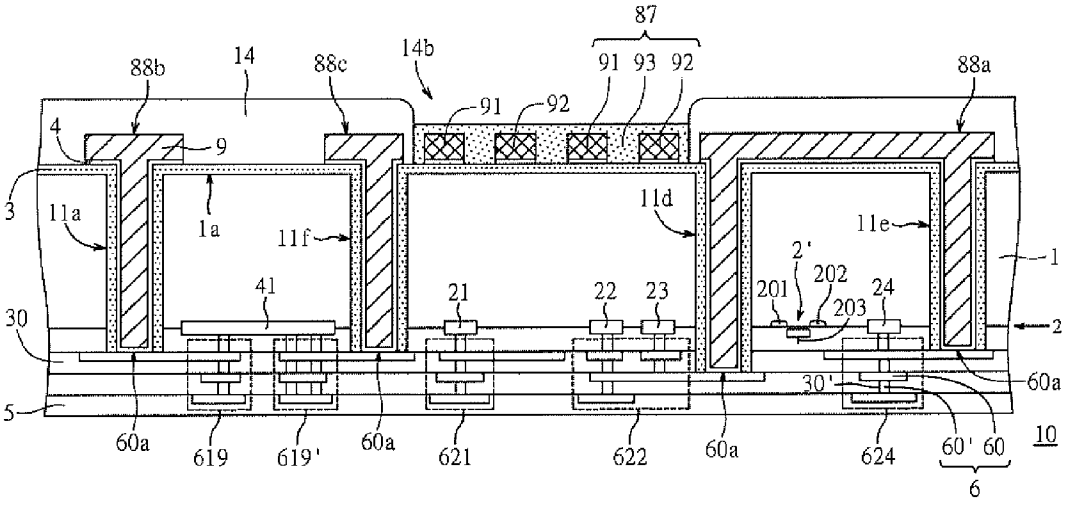


Fig. 33H

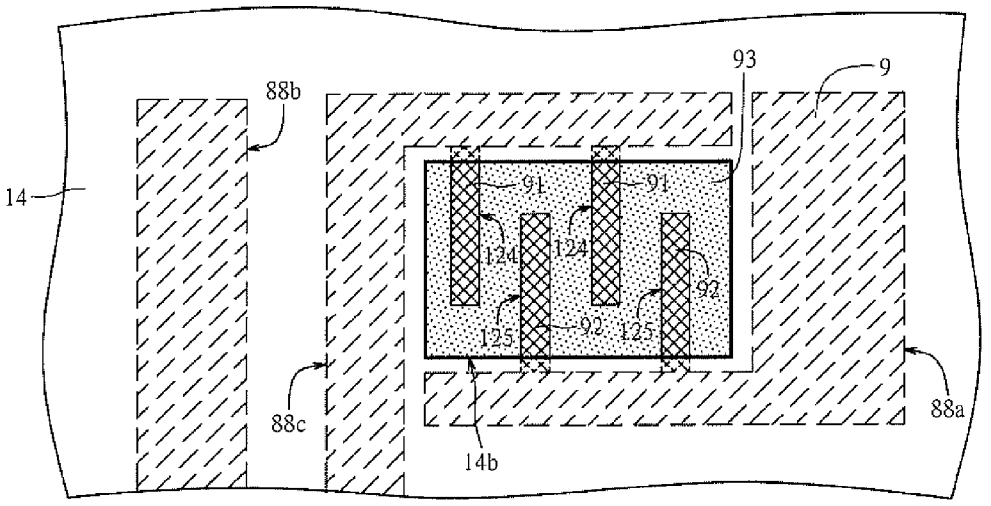


Fig. 33I

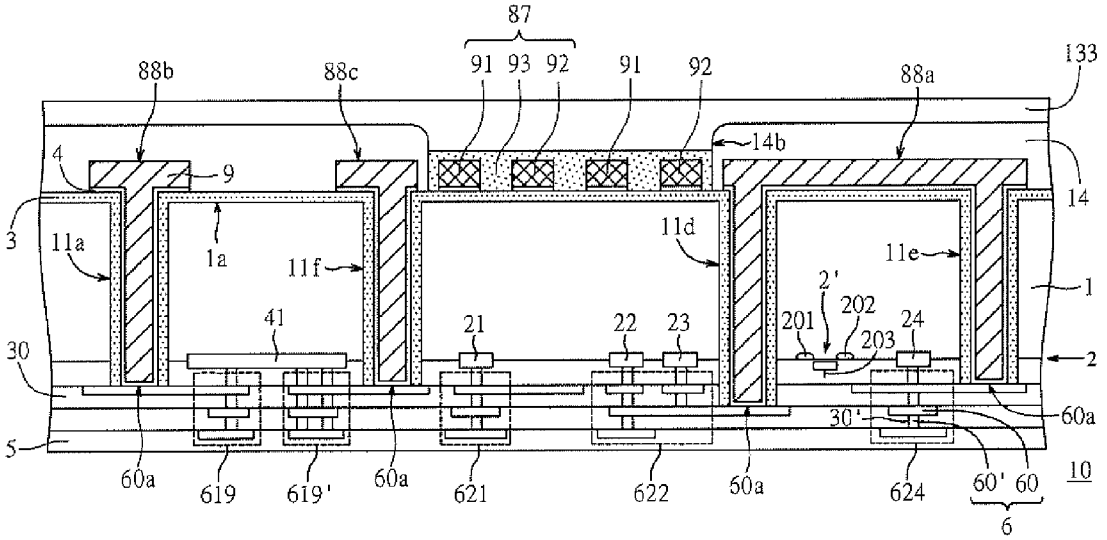


Fig. 33J

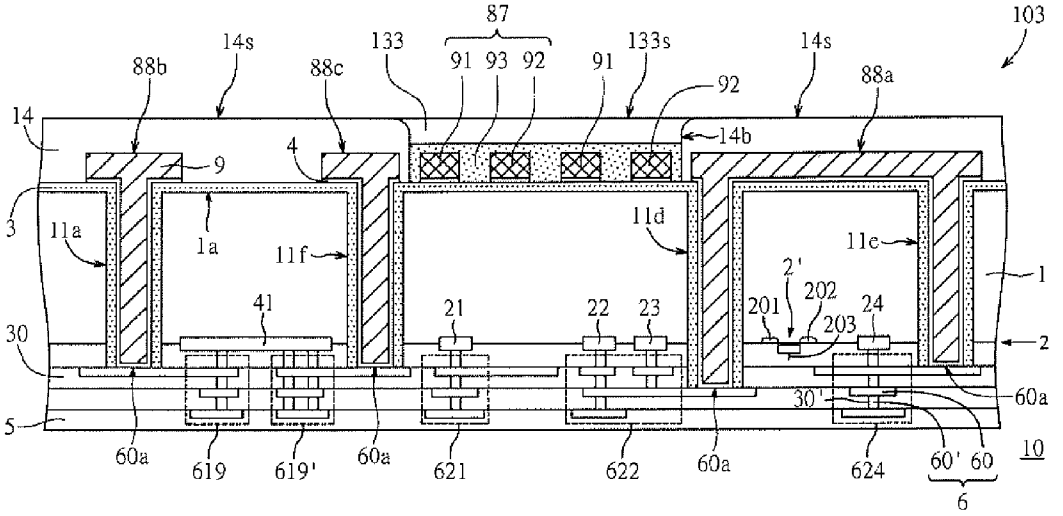


Fig. 33K

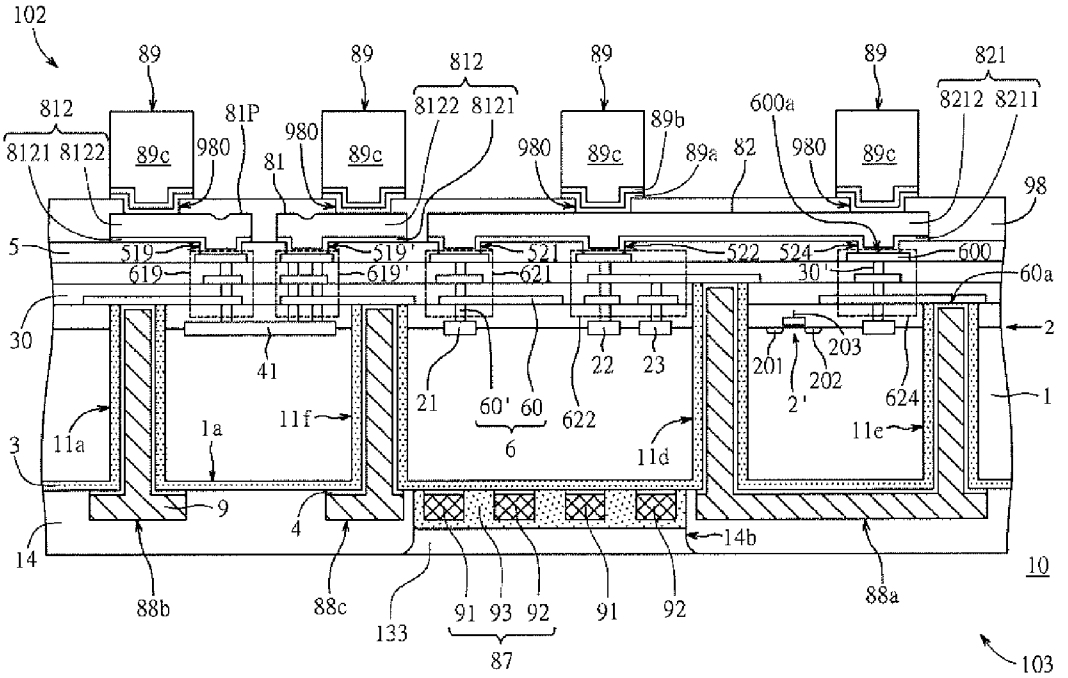


Fig. 33L

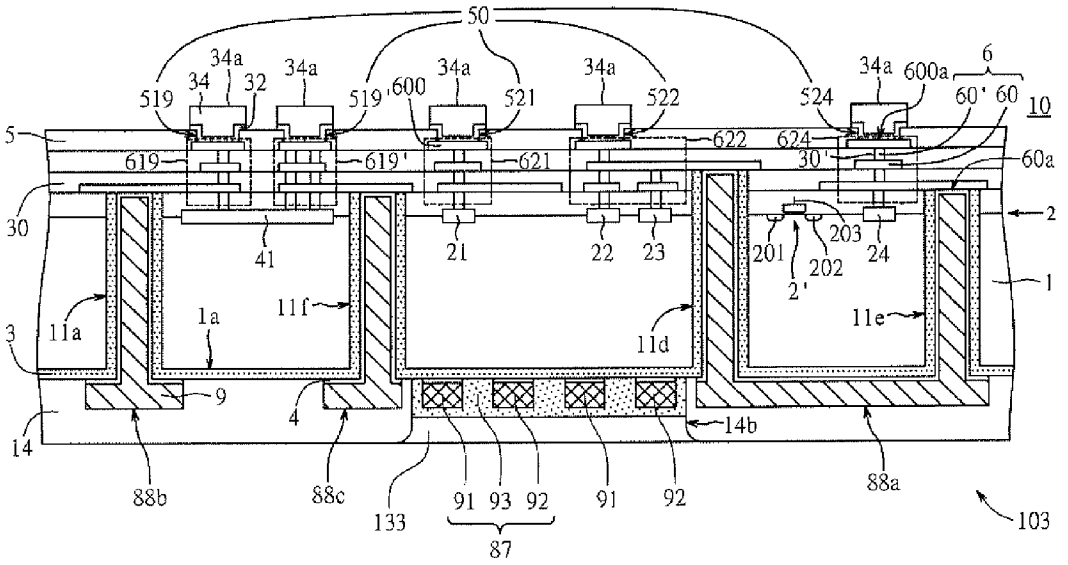


Fig. 33M

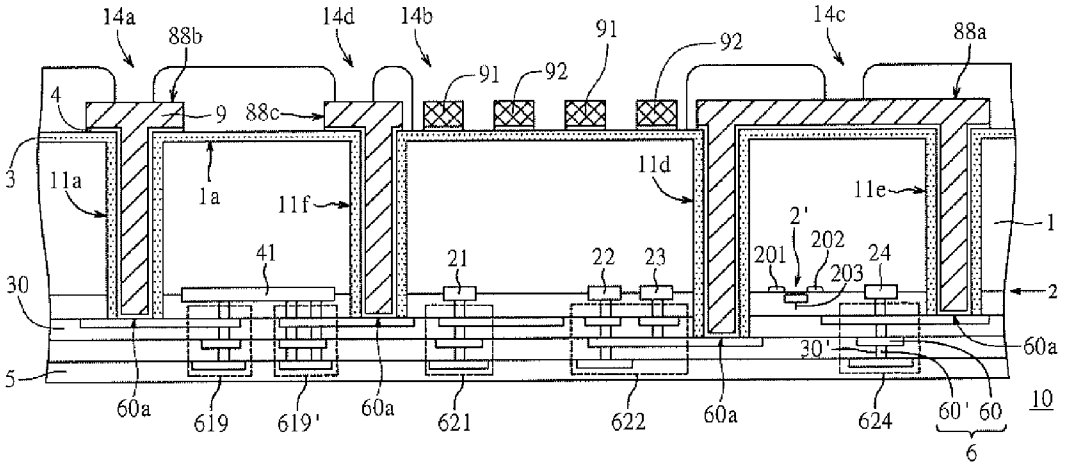


Fig. 33N

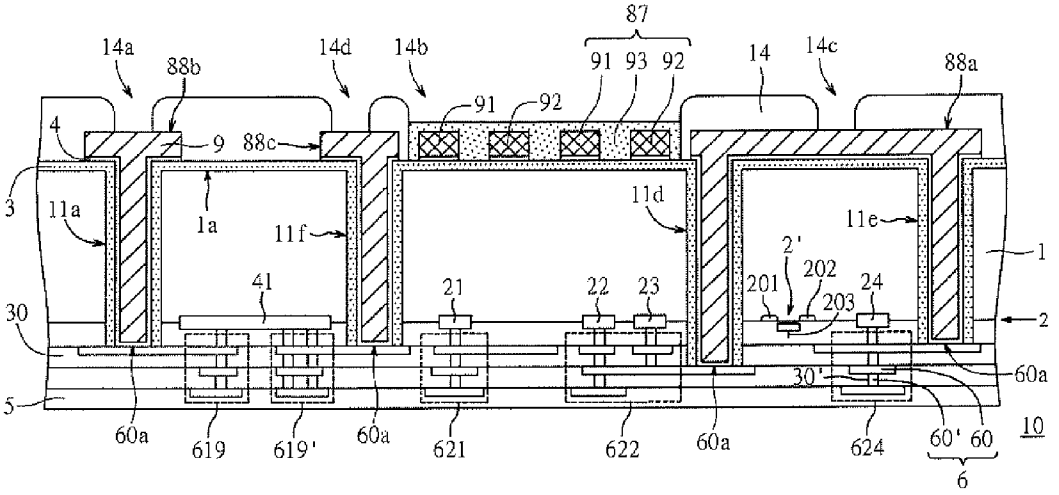


Fig. 33O

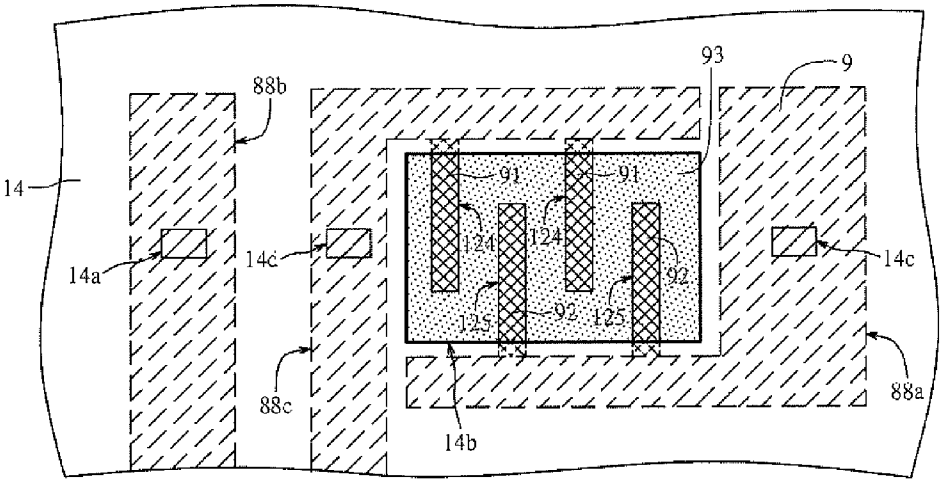


Fig. 33P

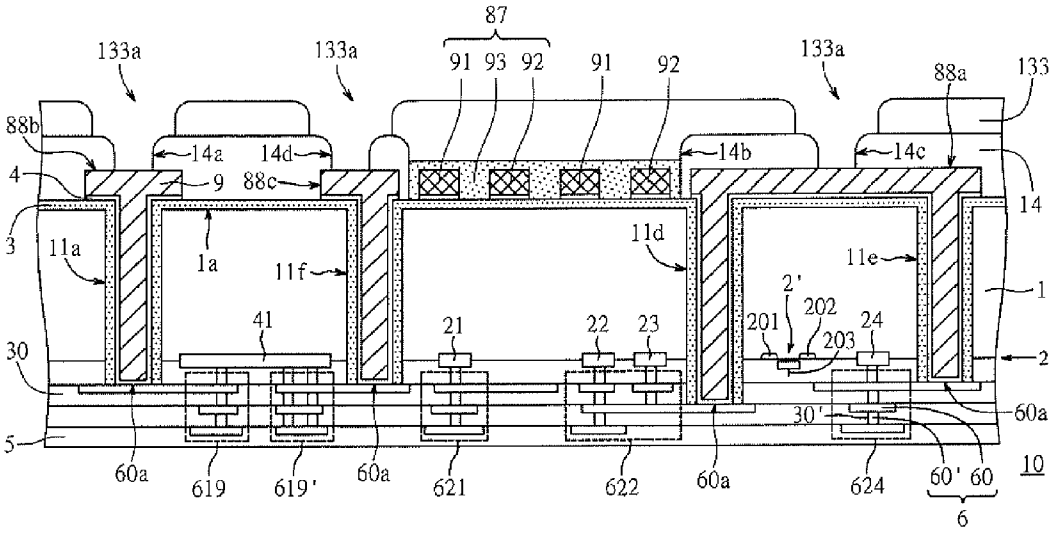


Fig. 33Q

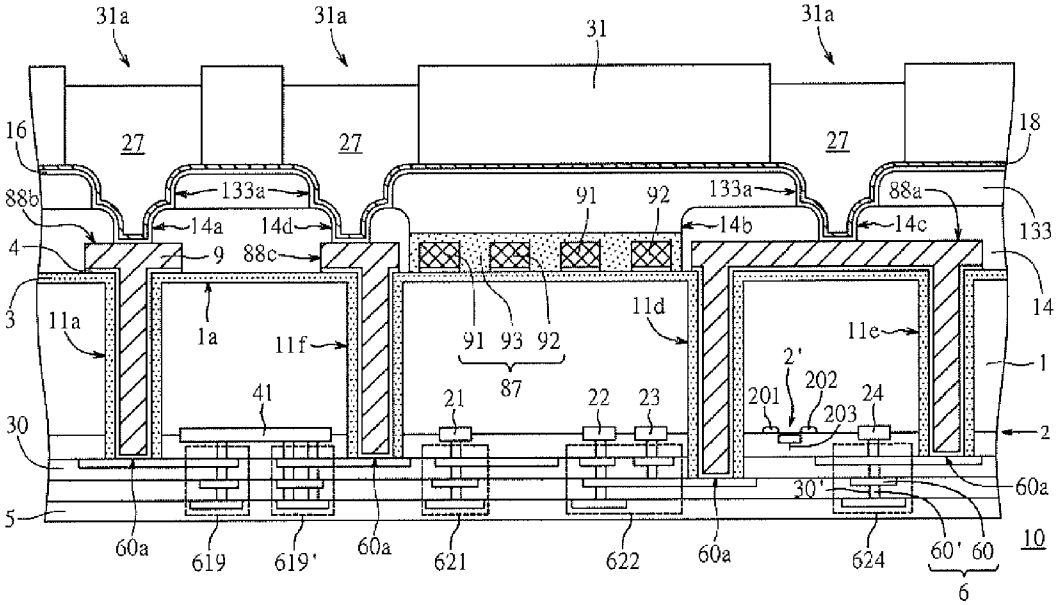


Fig. 33R

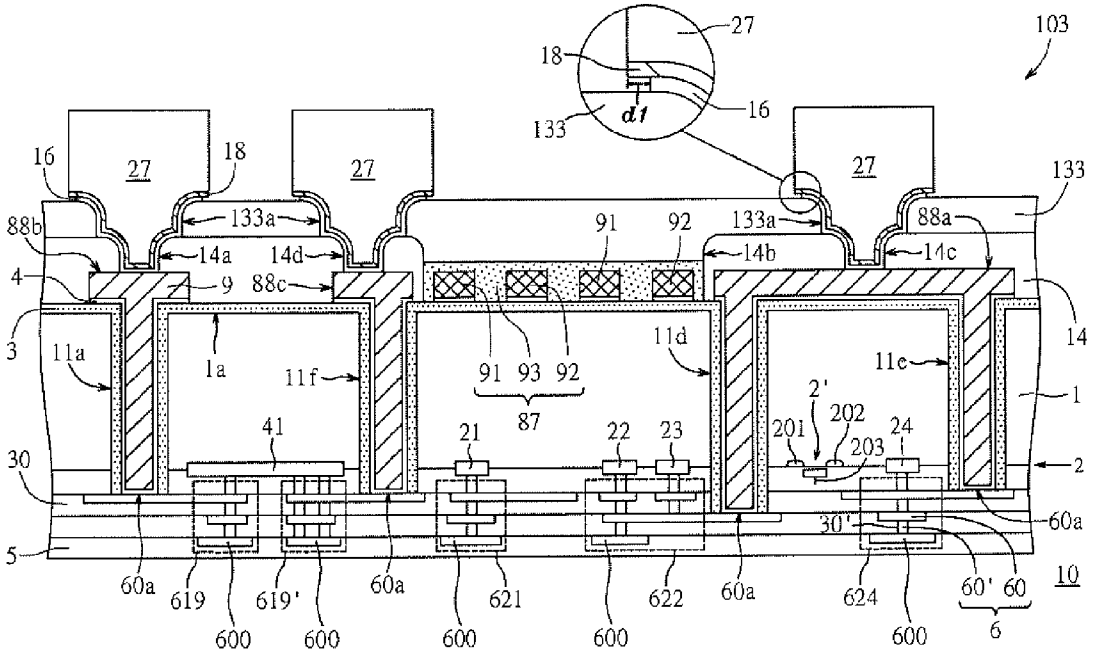


Fig. 33S

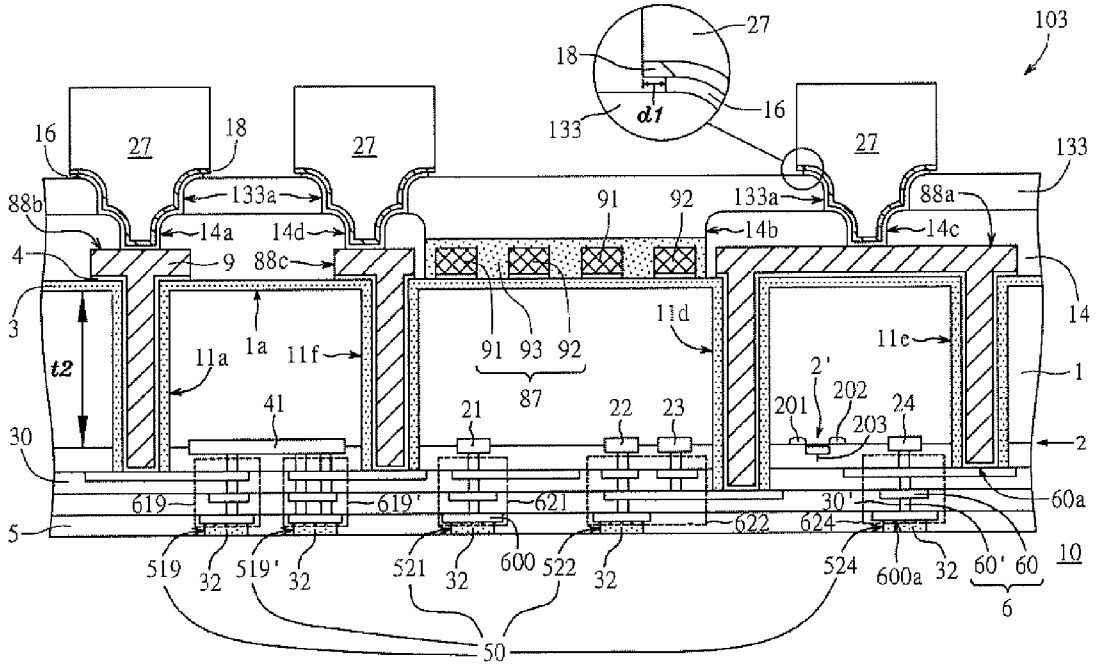


Fig. 33T

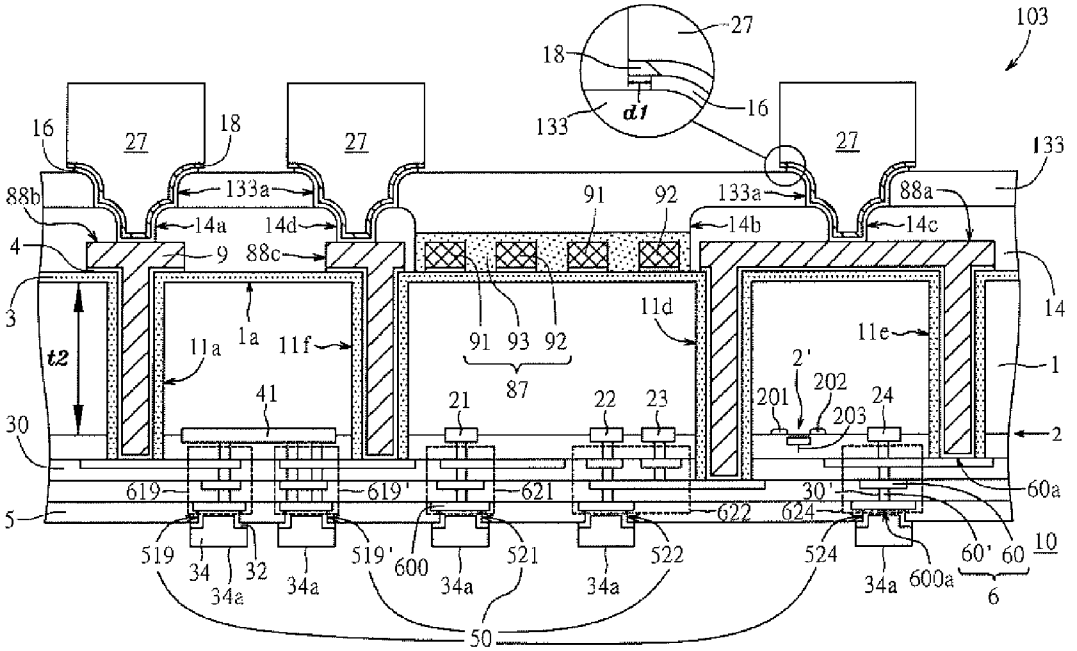


Fig. 33U

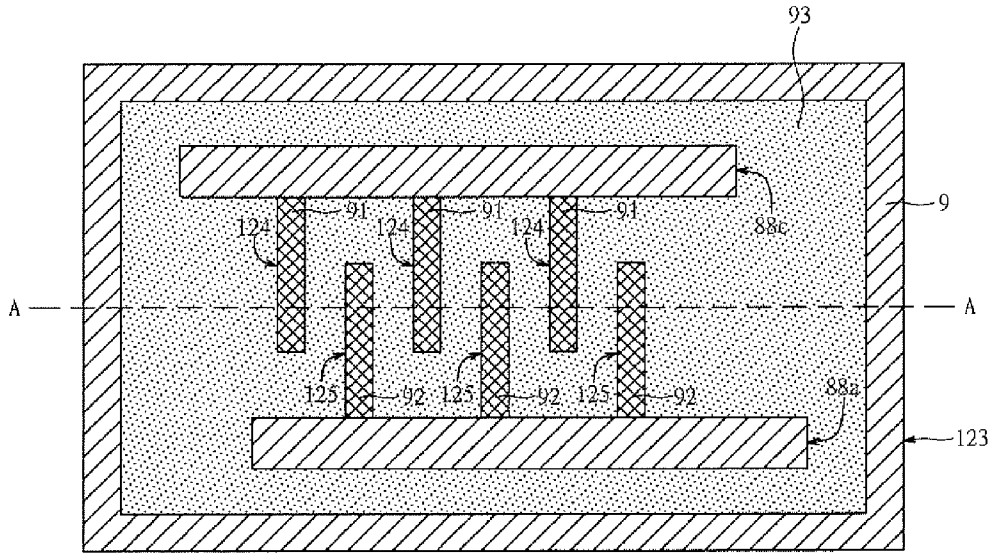


Fig. 33V

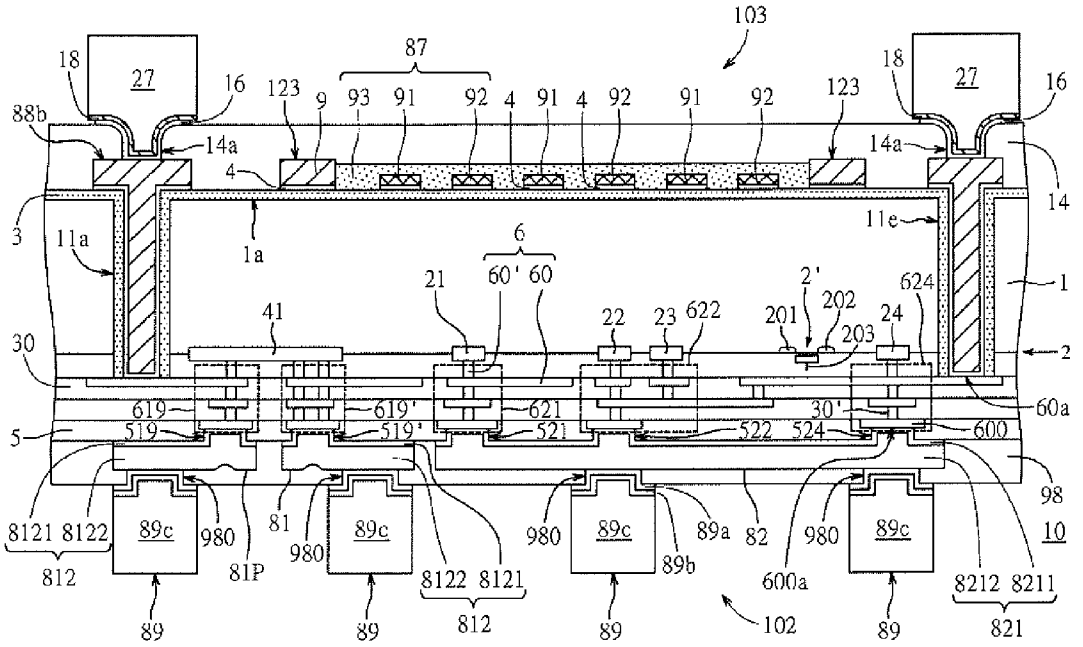


Fig. 33W

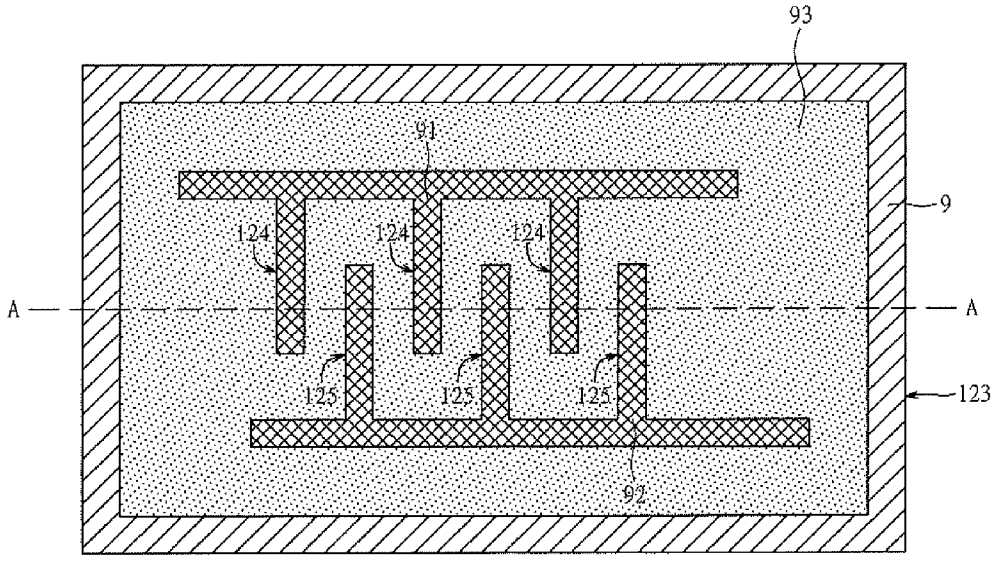


Fig. 33X

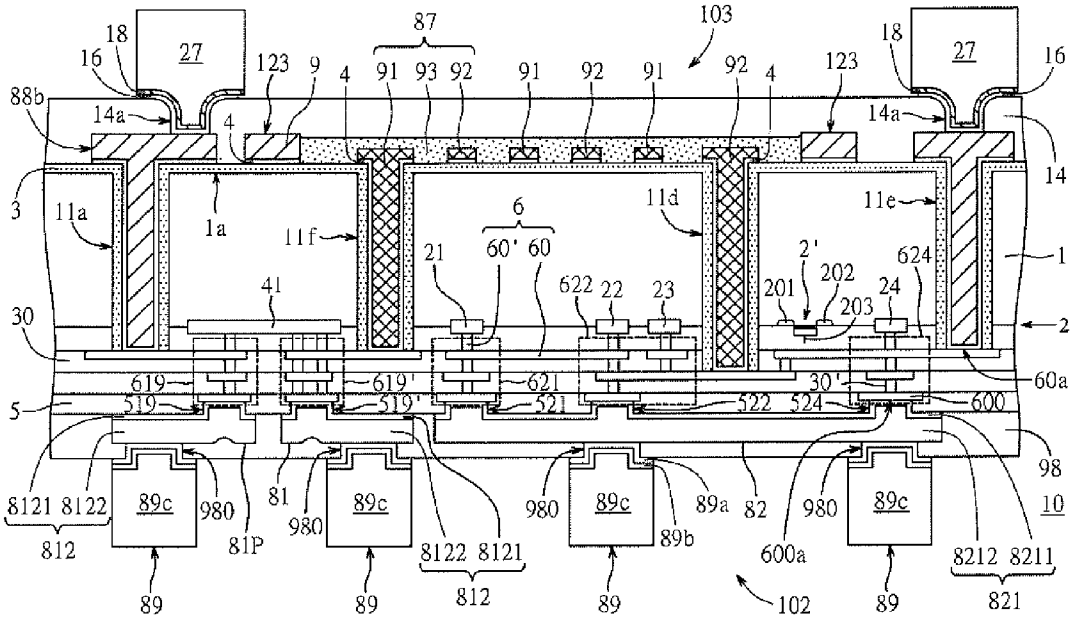


Fig. 33Y

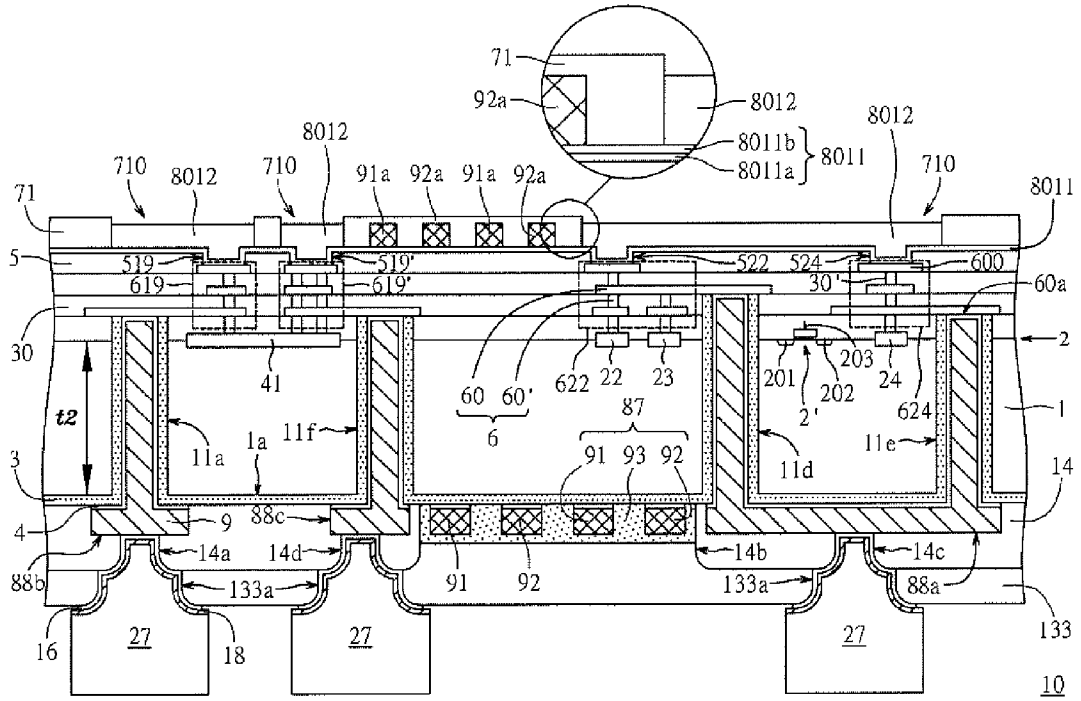


Fig. 34A

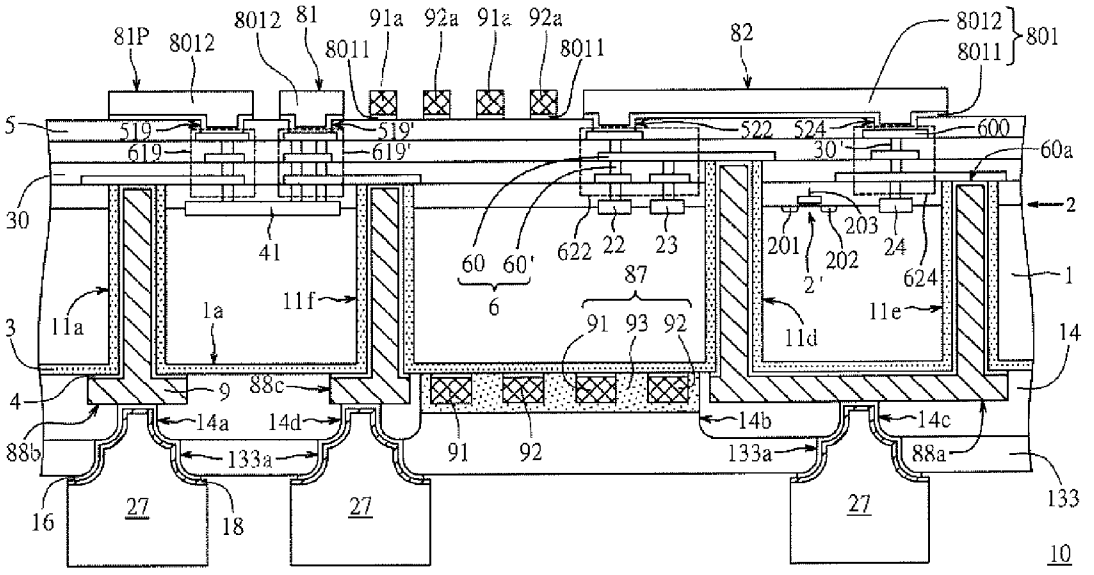


Fig. 34B

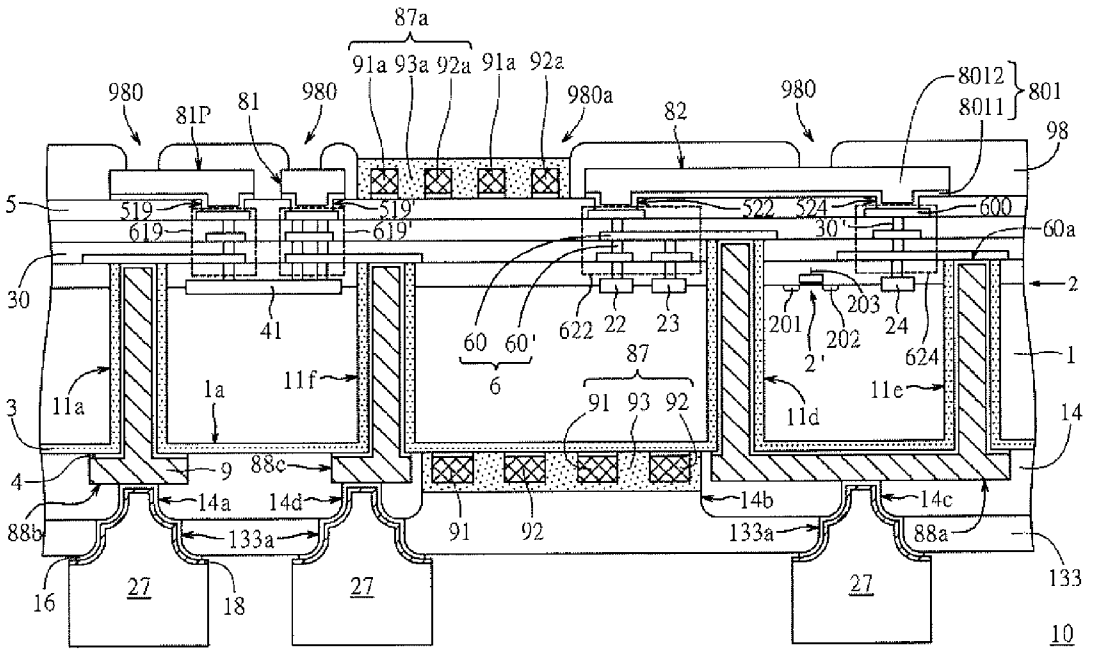


Fig. 34C

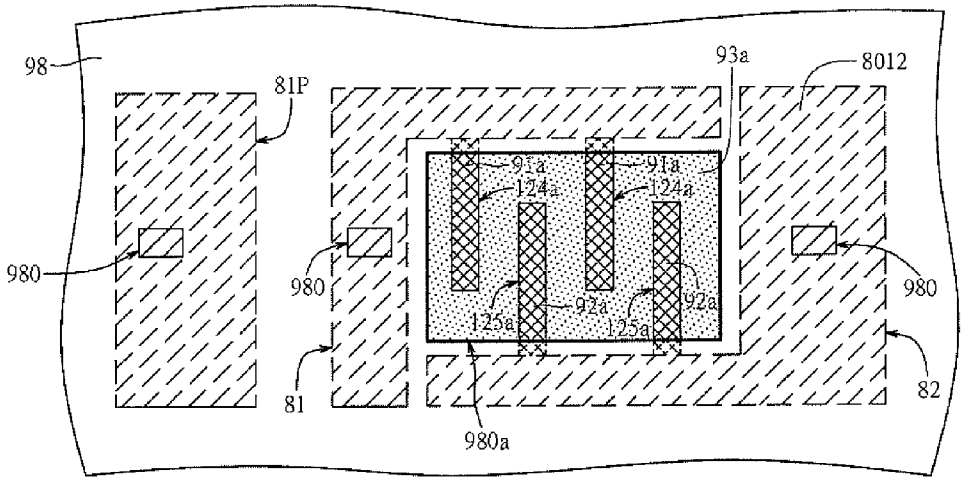


Fig. 34D

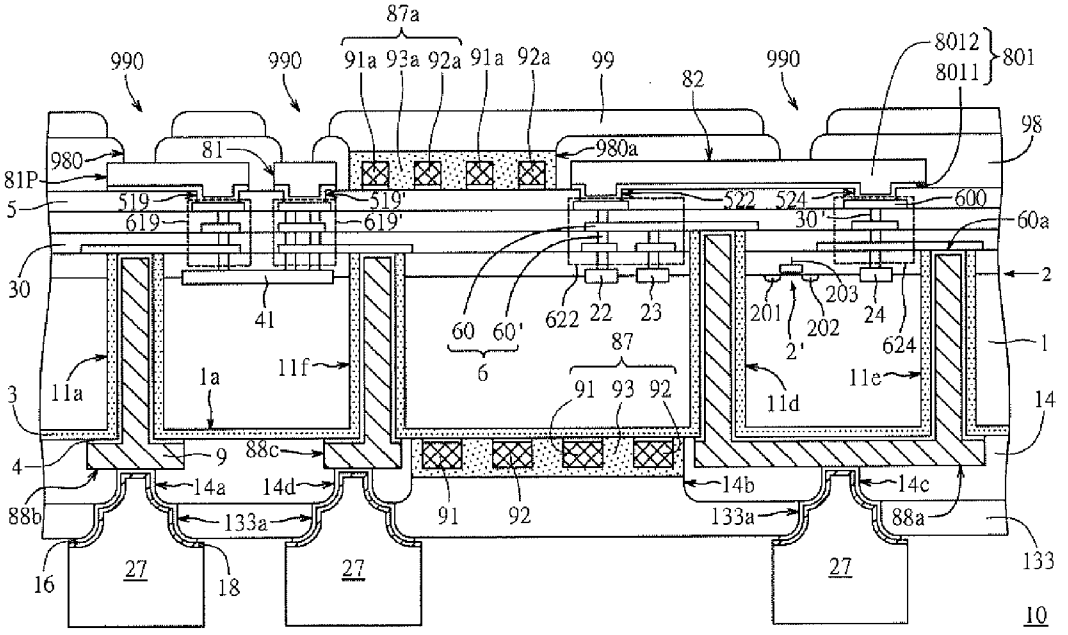


Fig. 34E

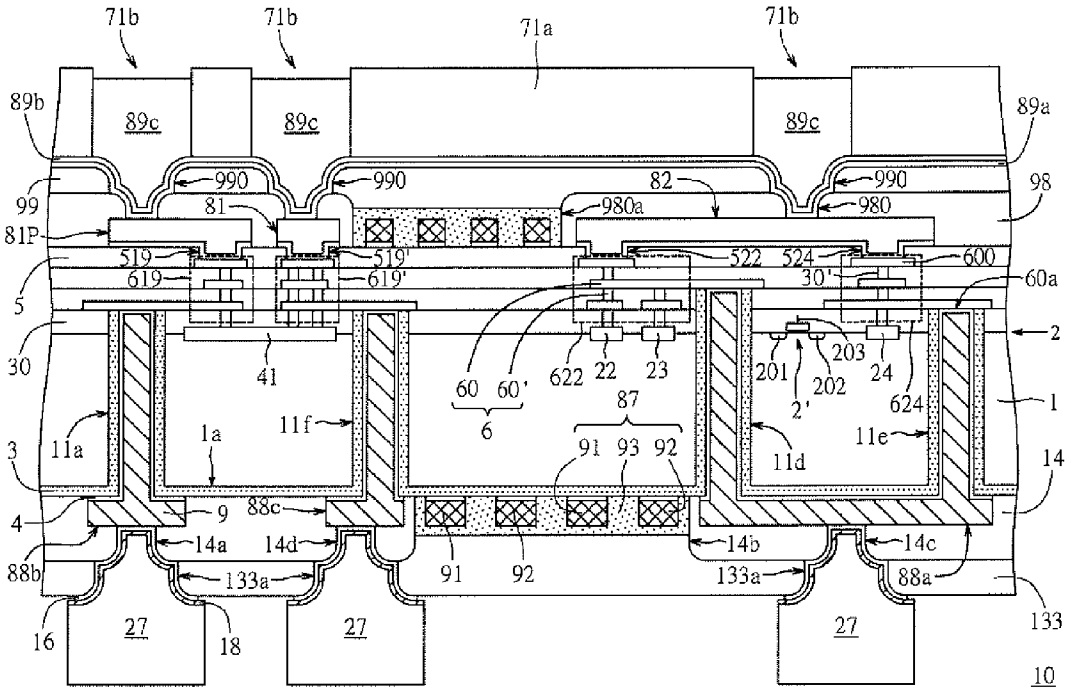


Fig. 34F

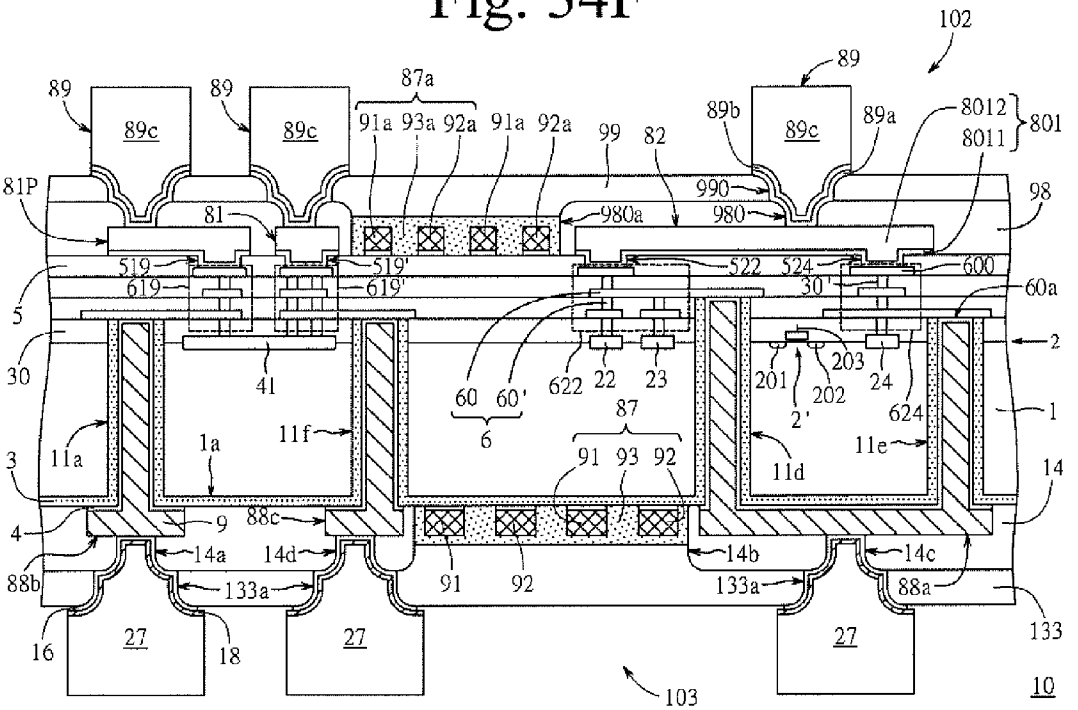


Fig. 34G

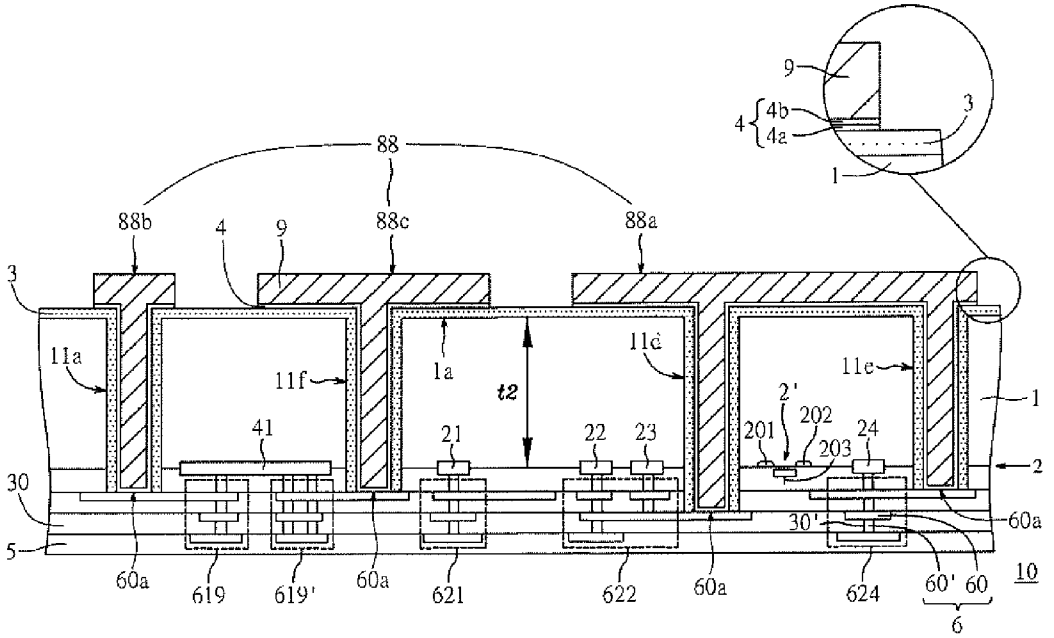


Fig. 35A

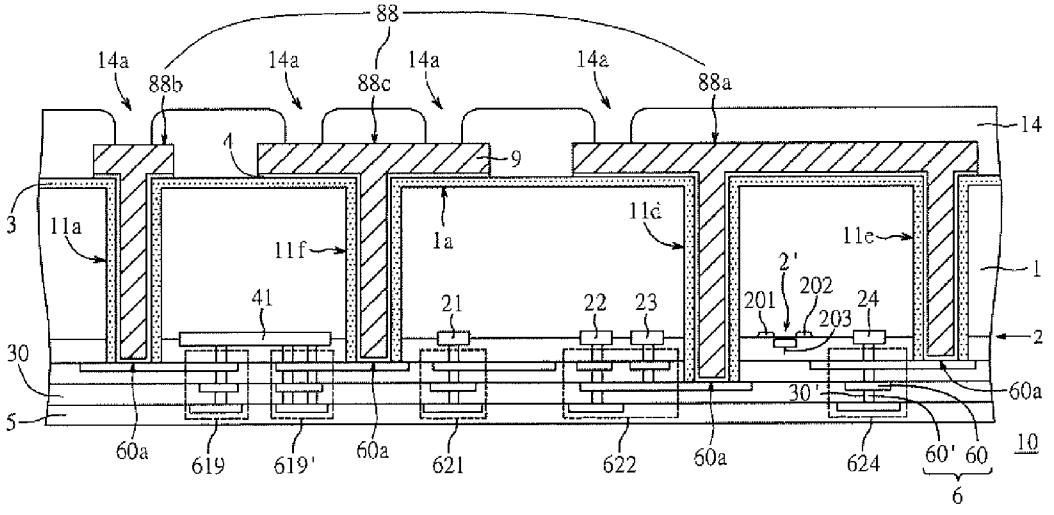


Fig. 35B

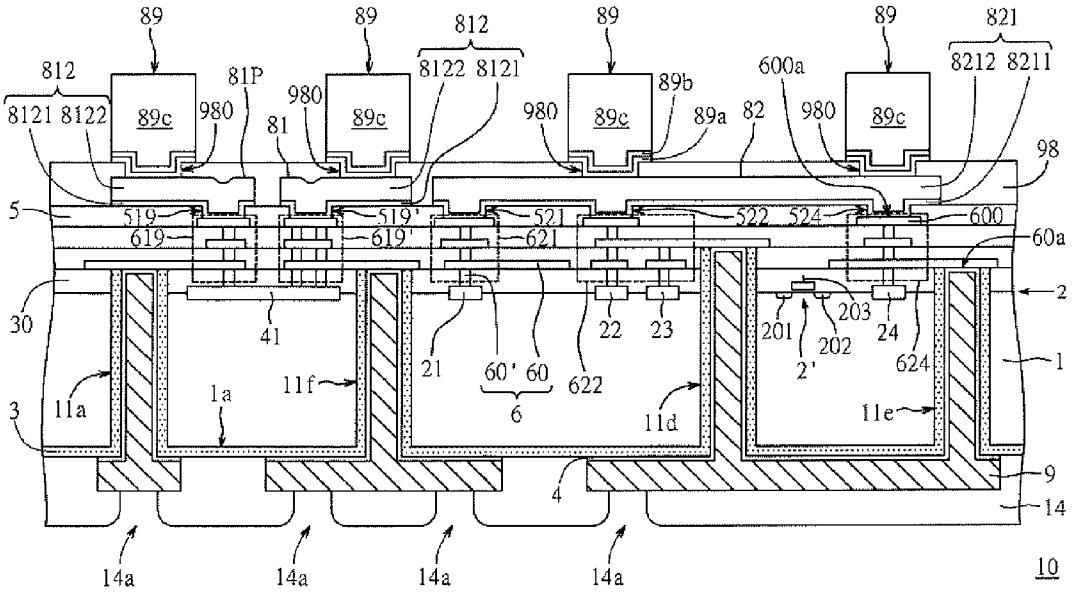


Fig. 35C

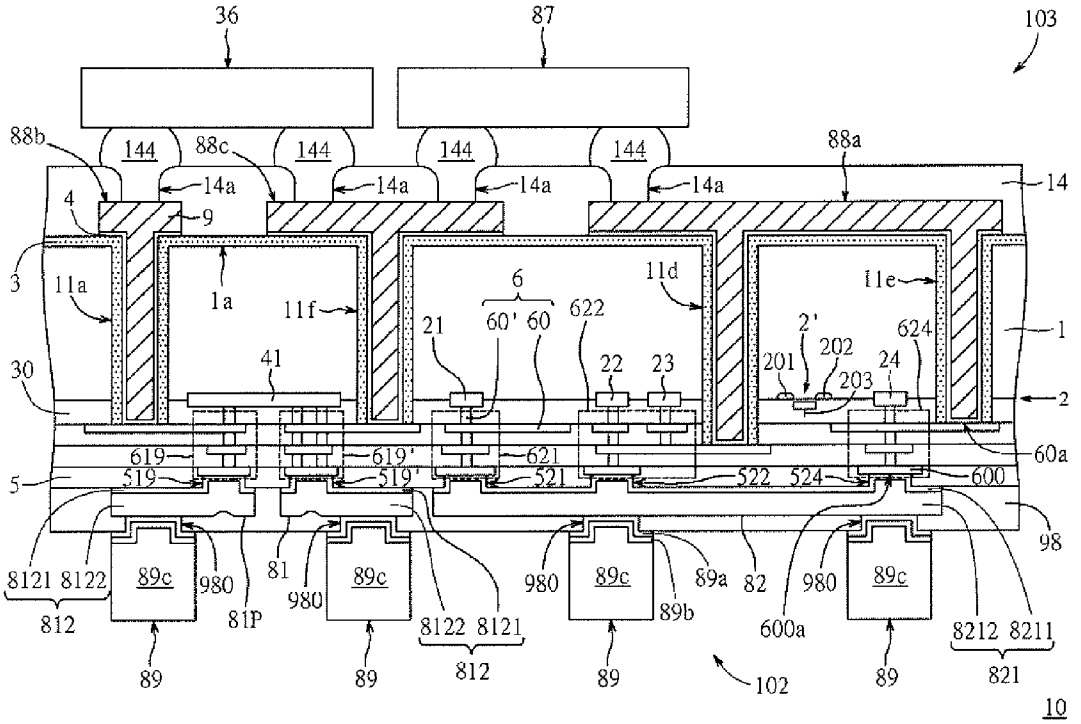


Fig. 35D

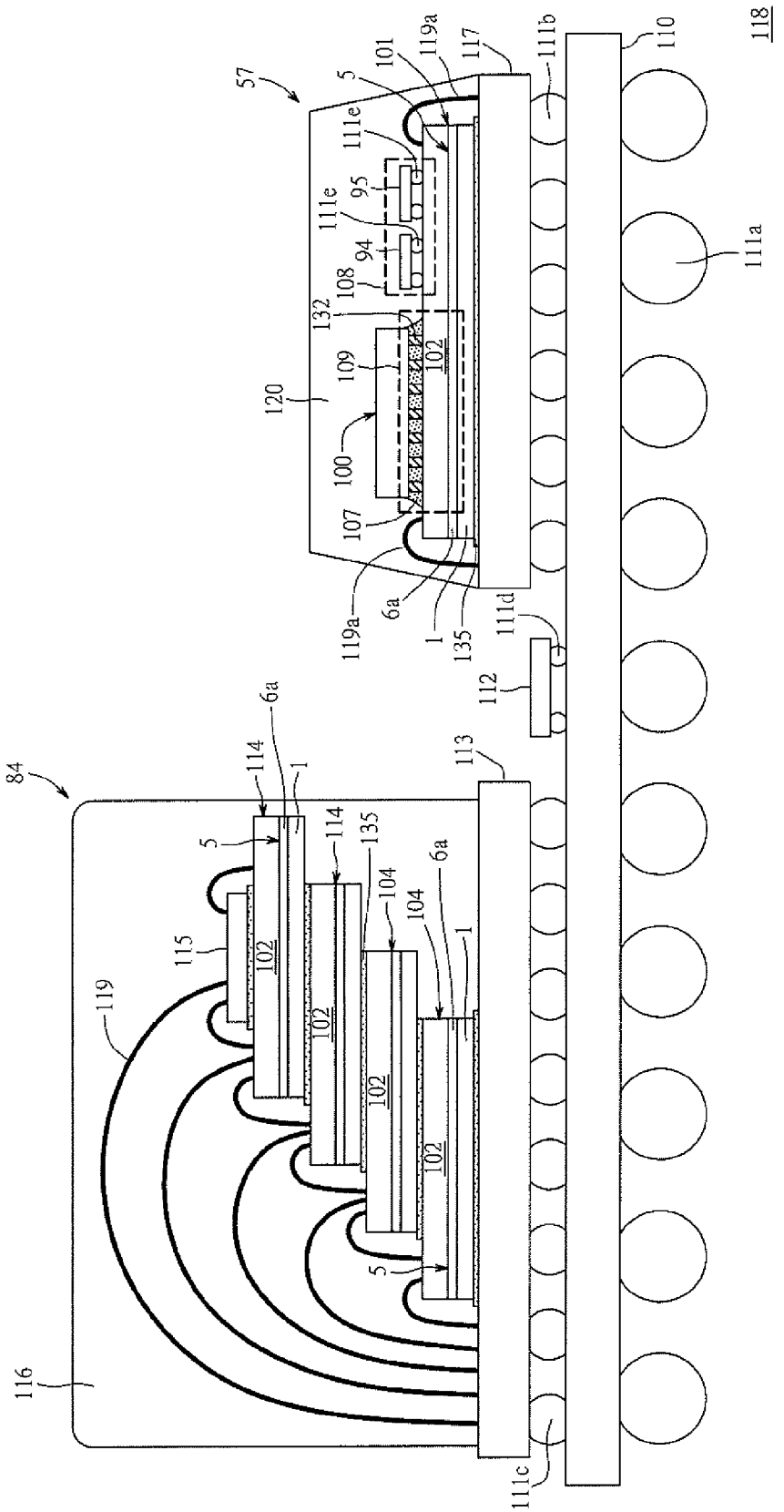

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Fig. 36A

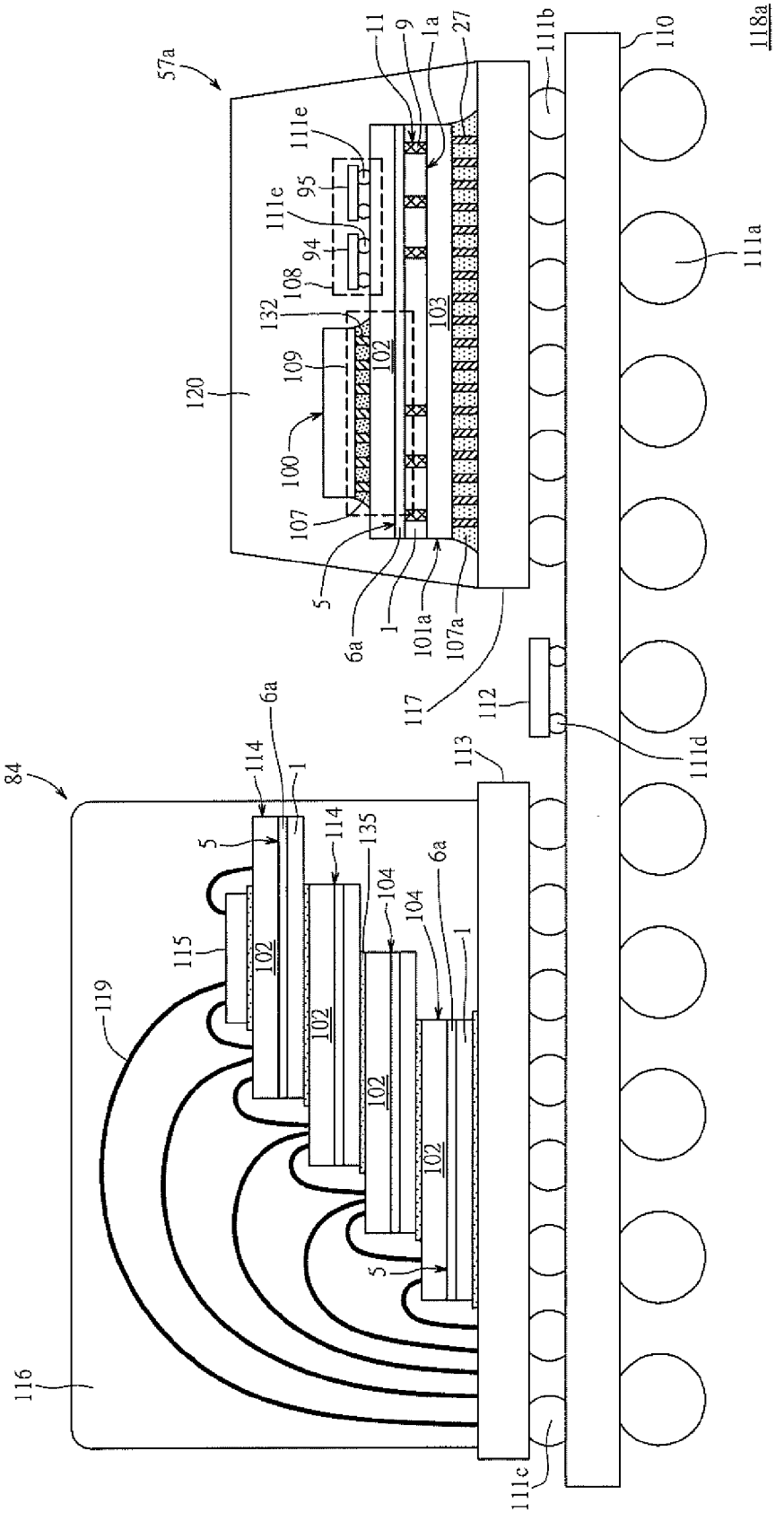

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111c

Fig. 36B

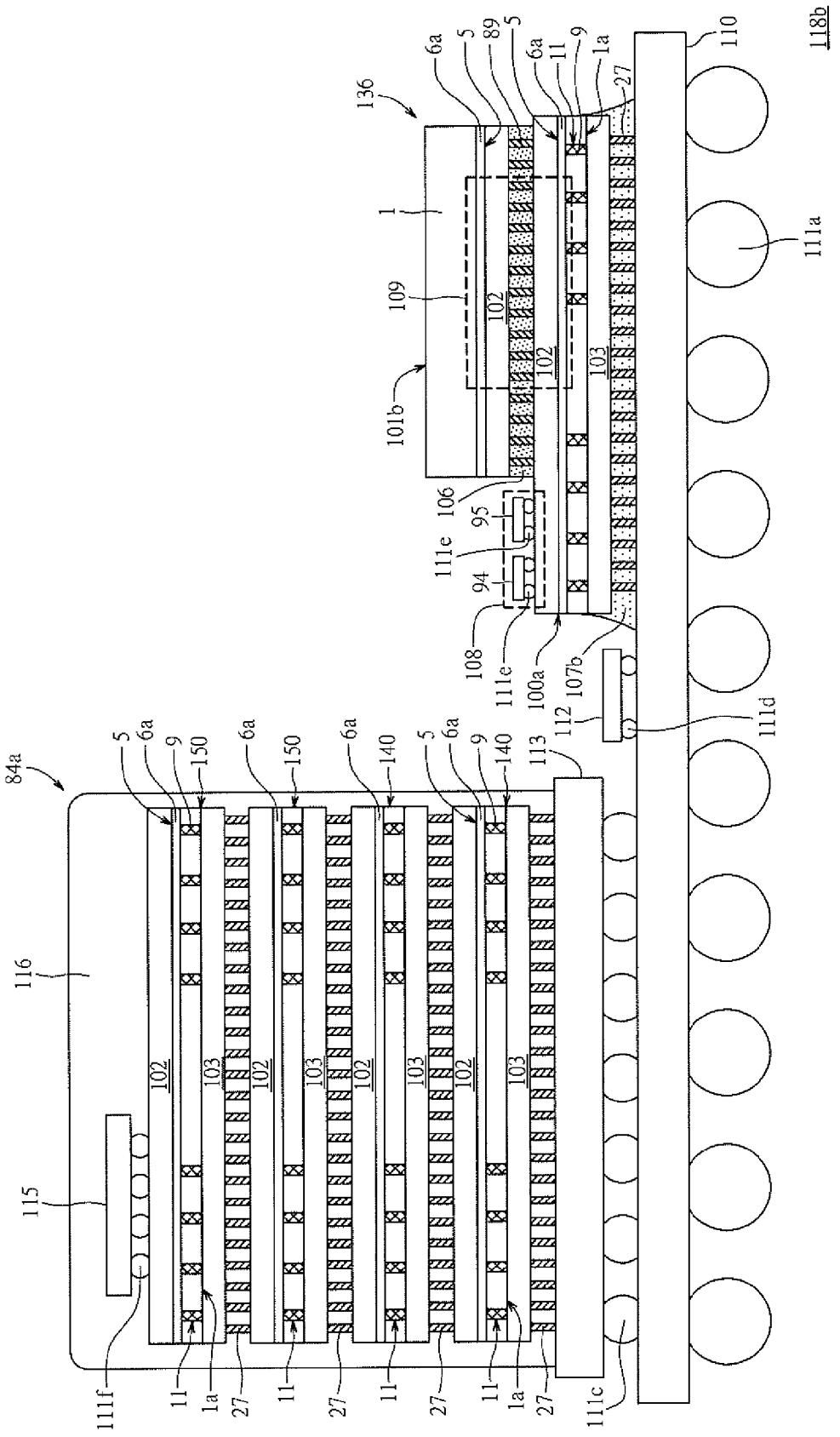

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111a
118b

Fig. 36C

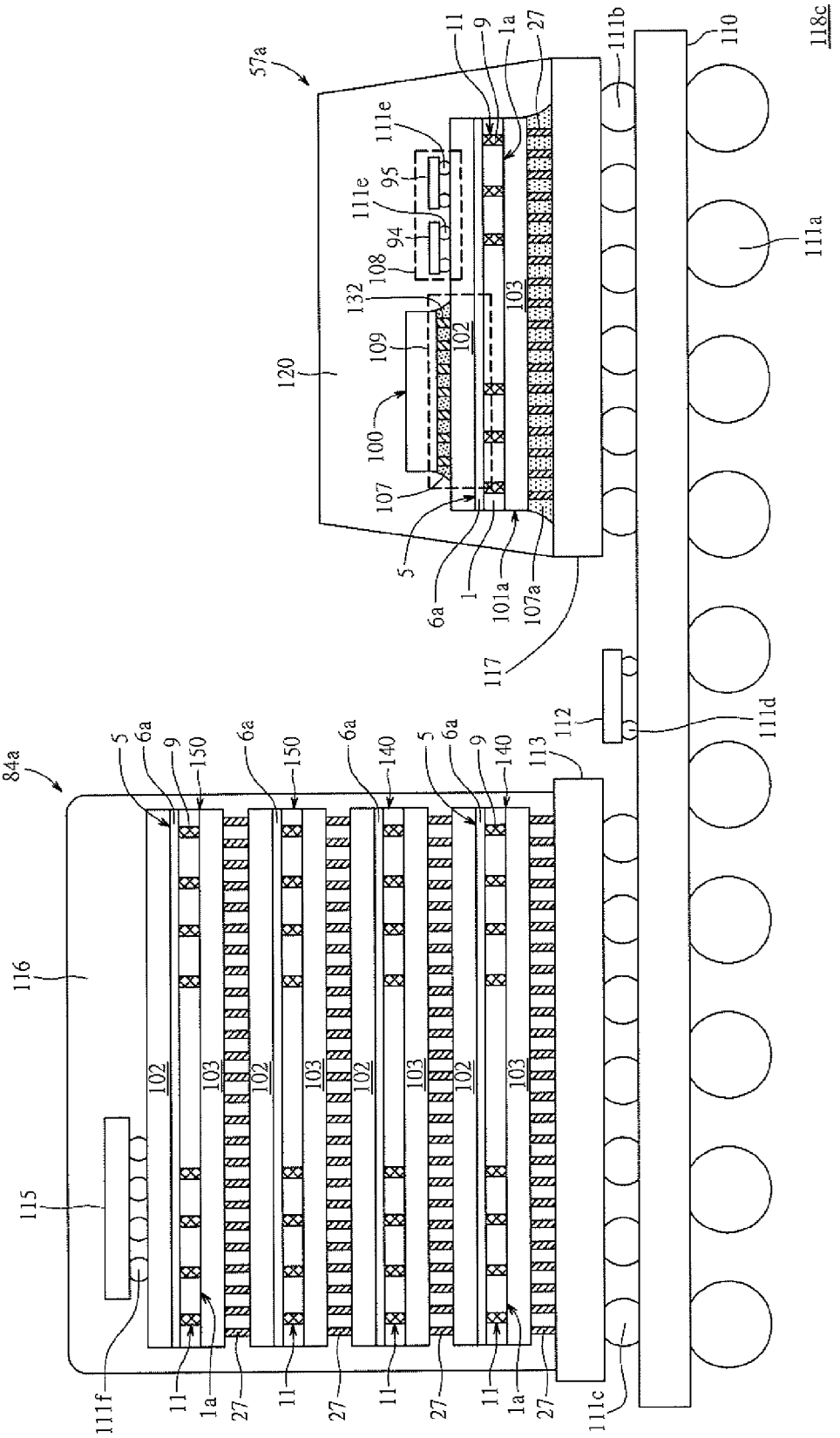

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111f
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27

Fig. 36D

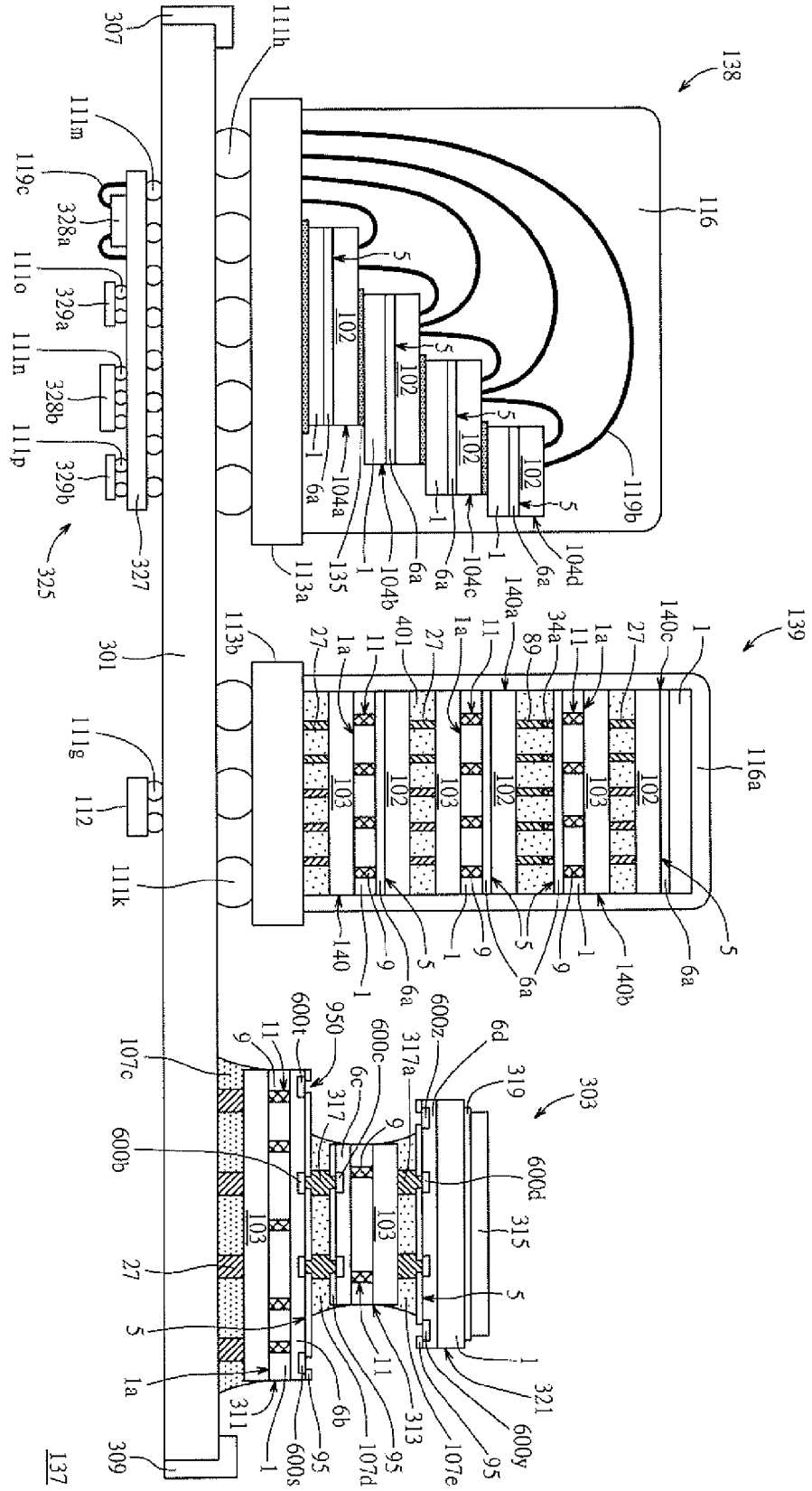

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328b
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111p
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140b
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309
137

Fig. 37A

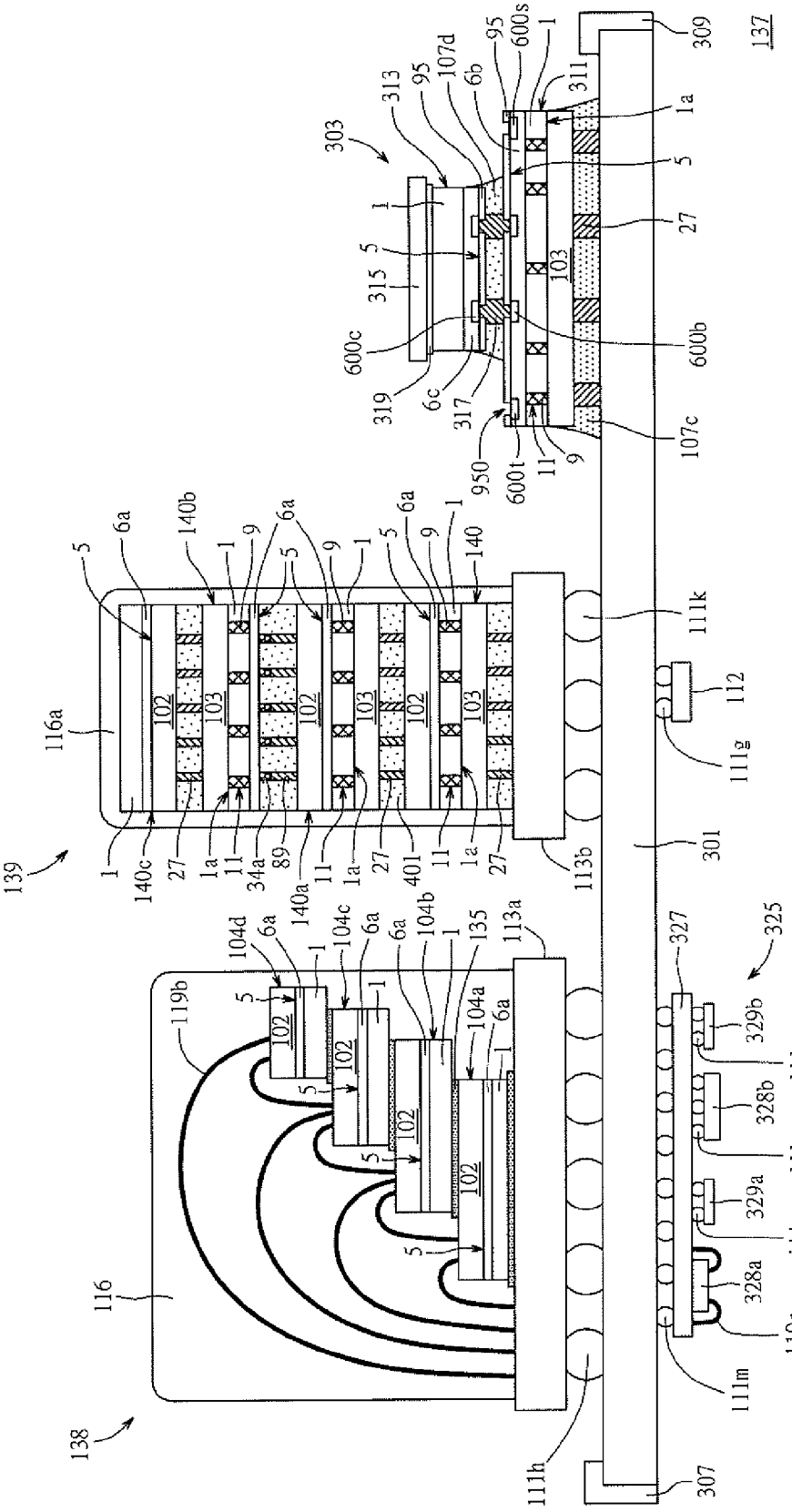

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107c
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111g
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140b
6a
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140c
34a
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104d
104c
104b
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119b
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307
327
325
329b
328b
111p
111n
329a
111o
328a
119c
111m

Fig. 37B

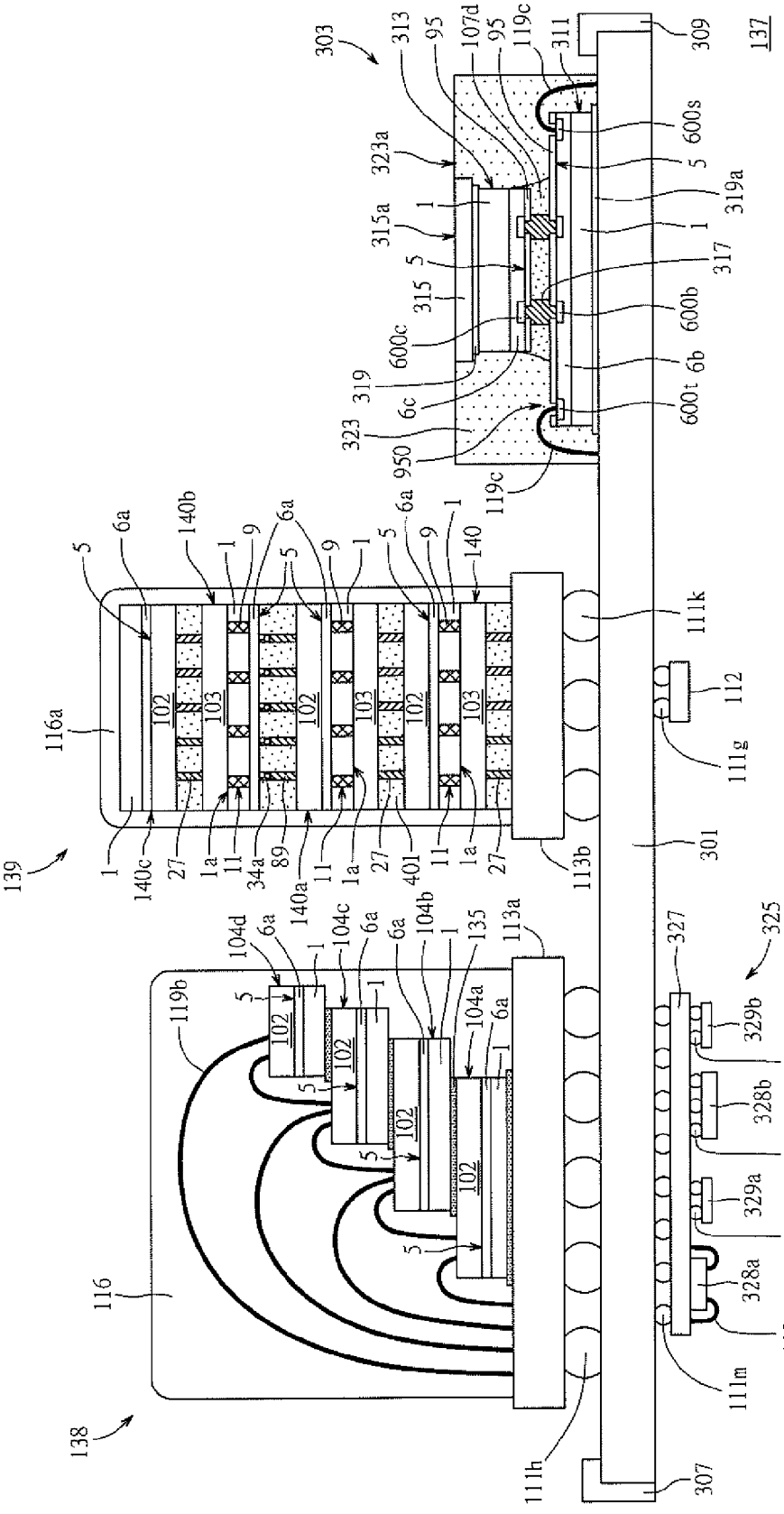


Fig. 37C

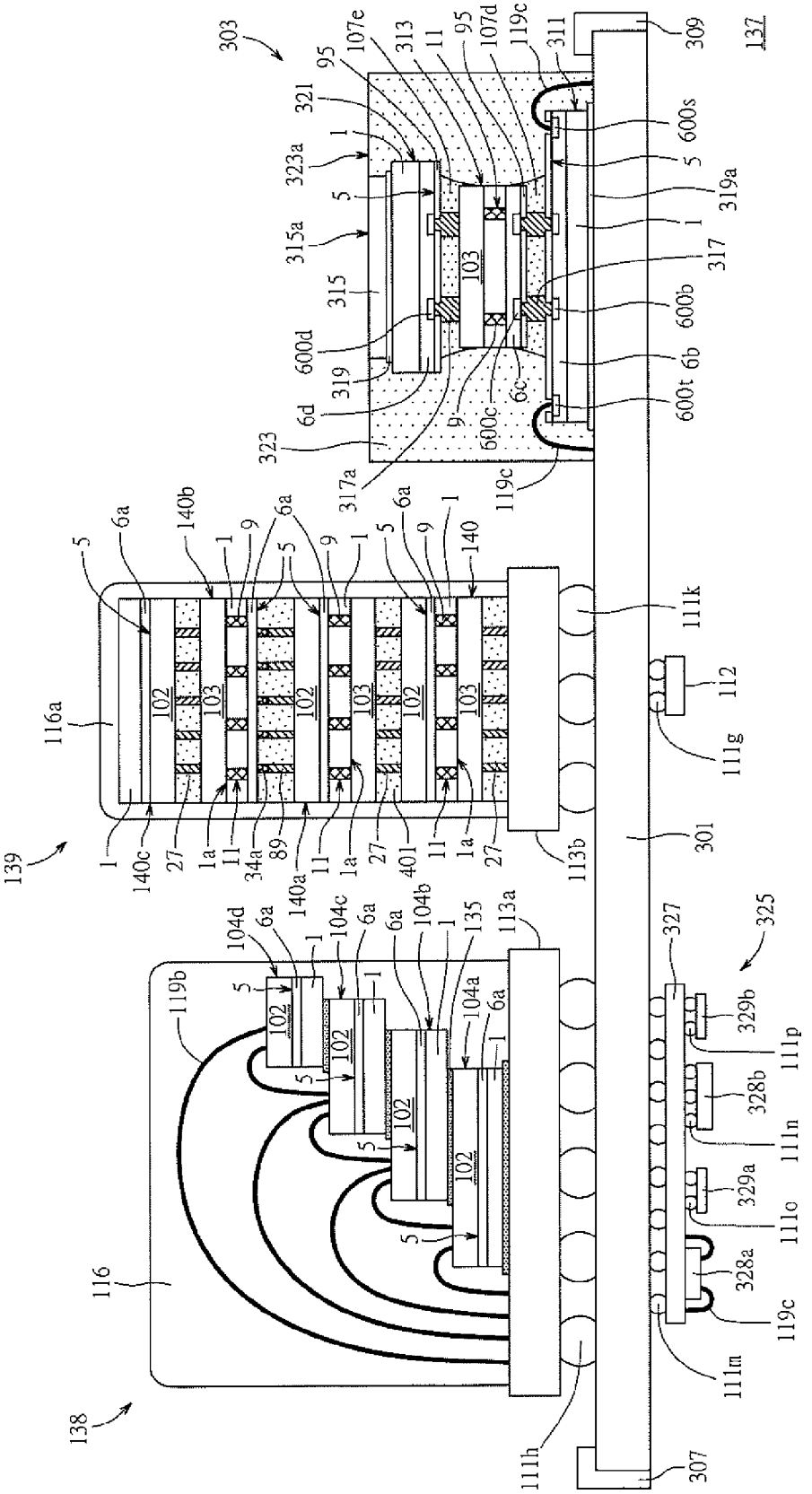


Fig. 37D

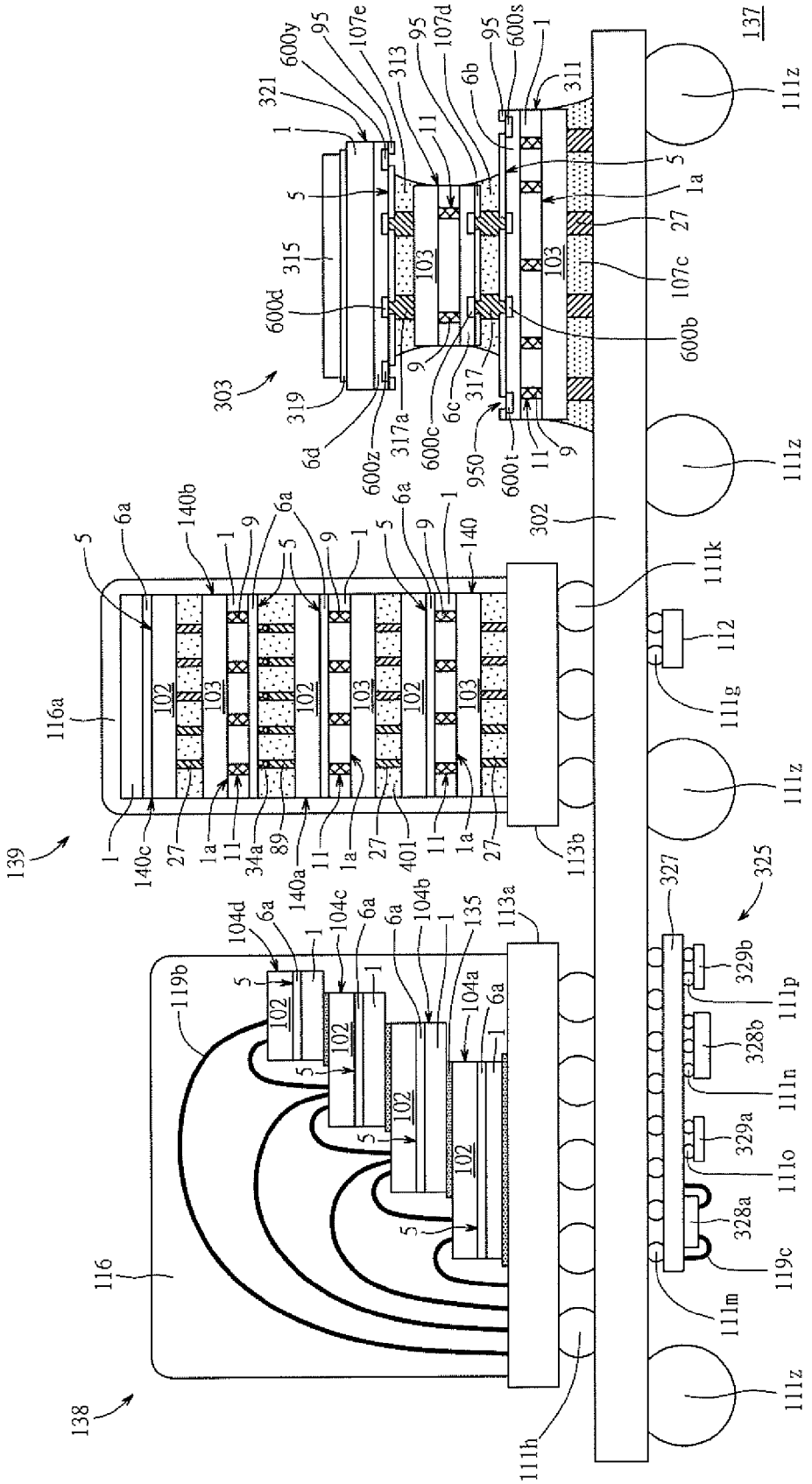


Fig. 38A

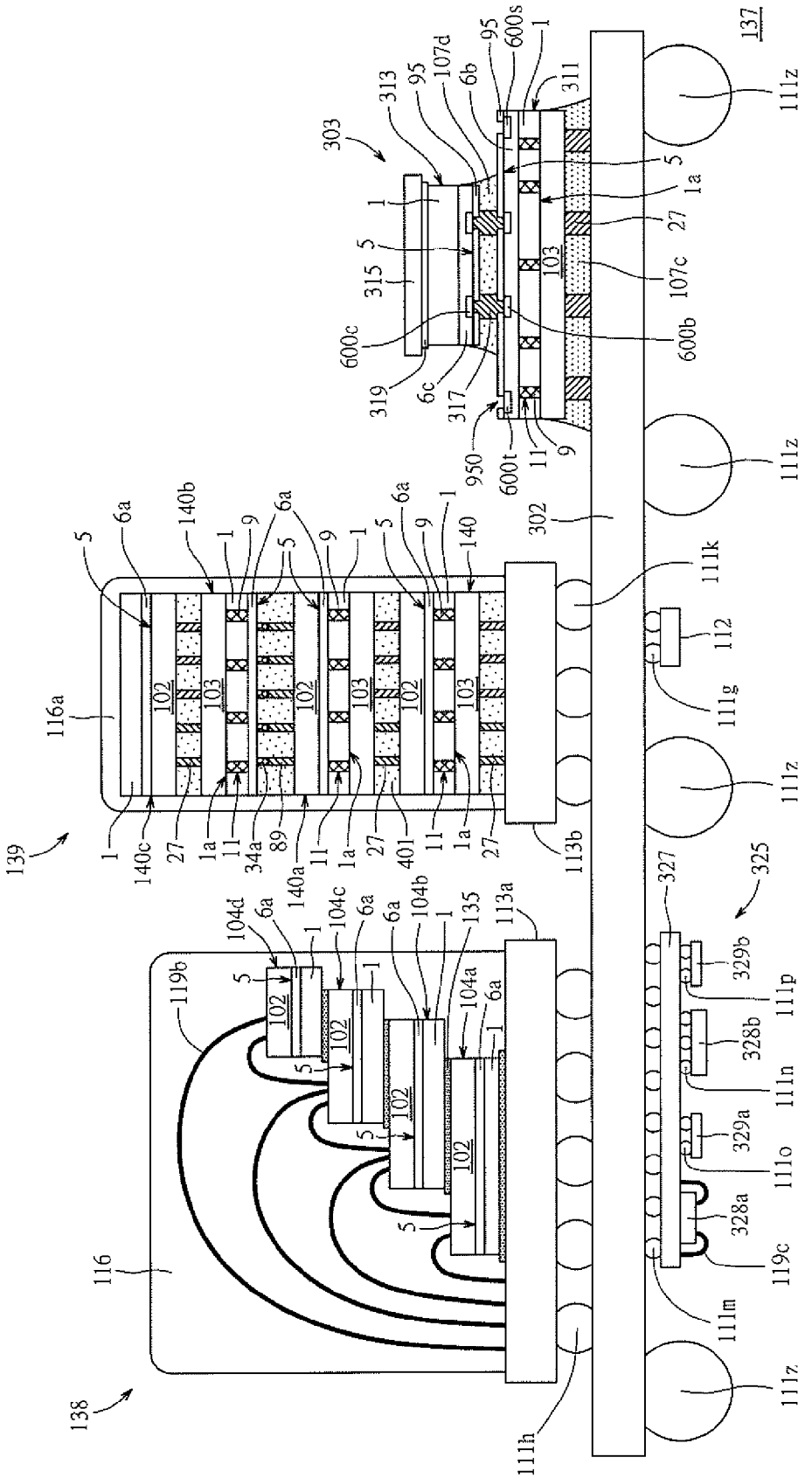


Fig. 38B

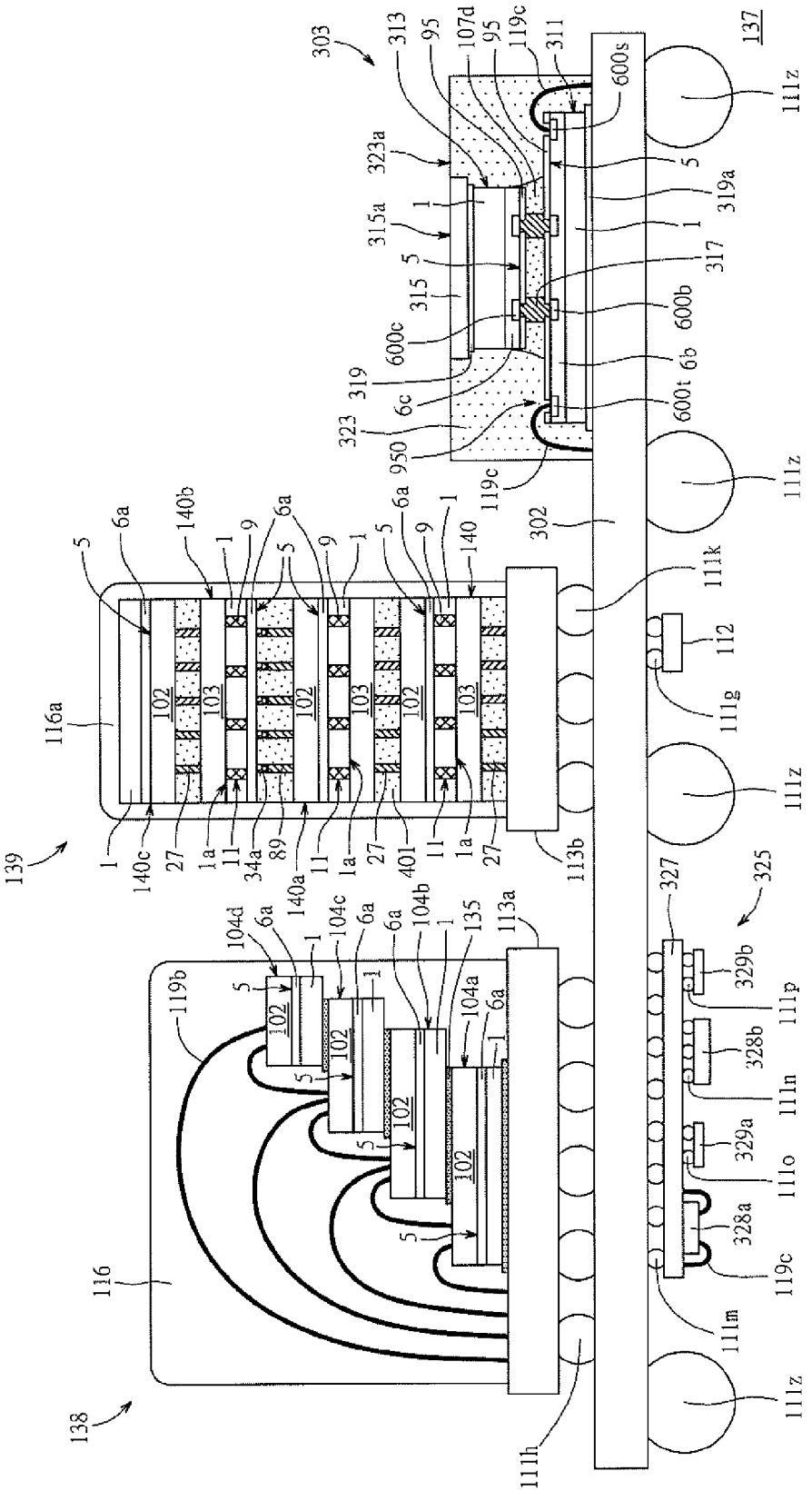


Fig. 38C

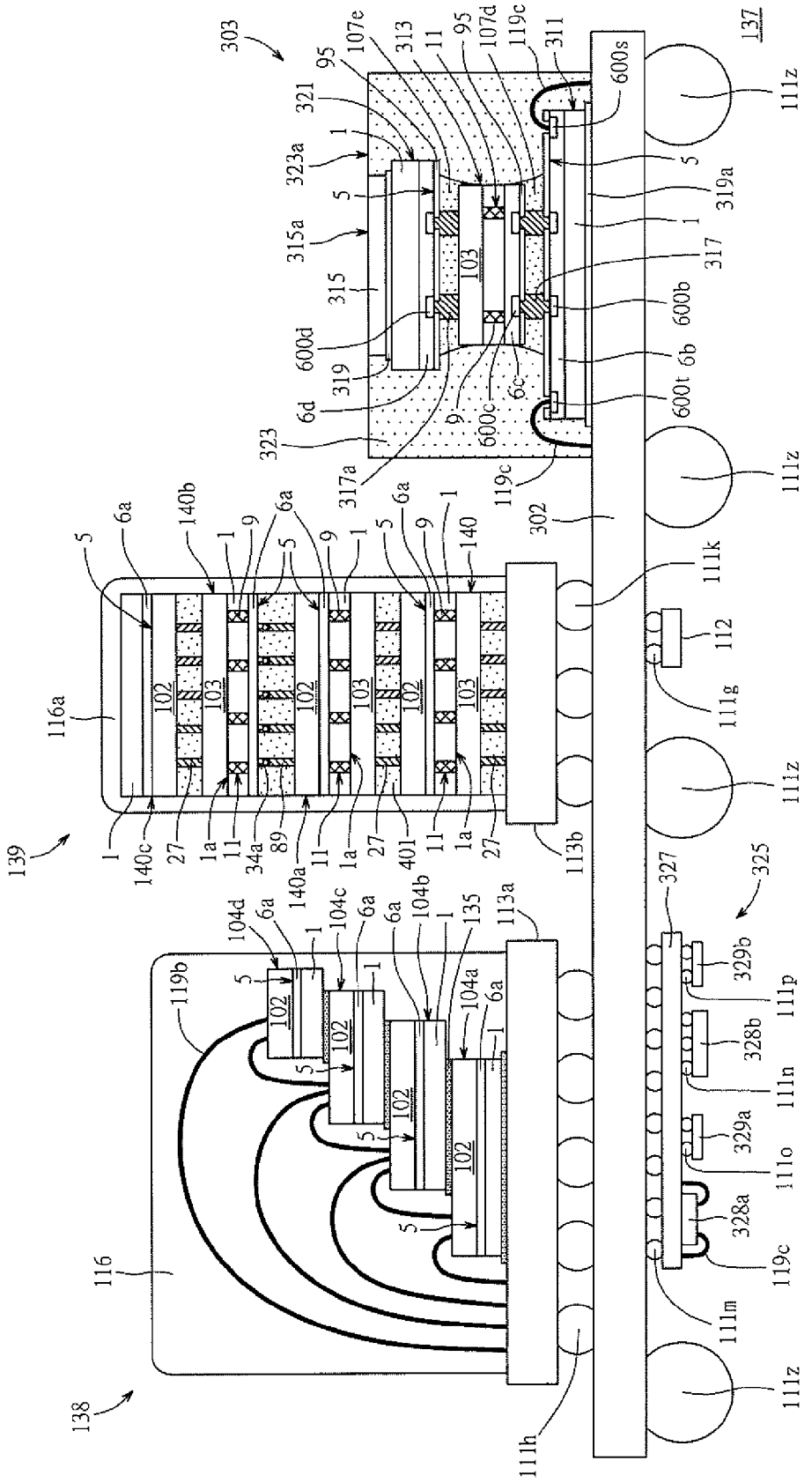


Fig. 38D

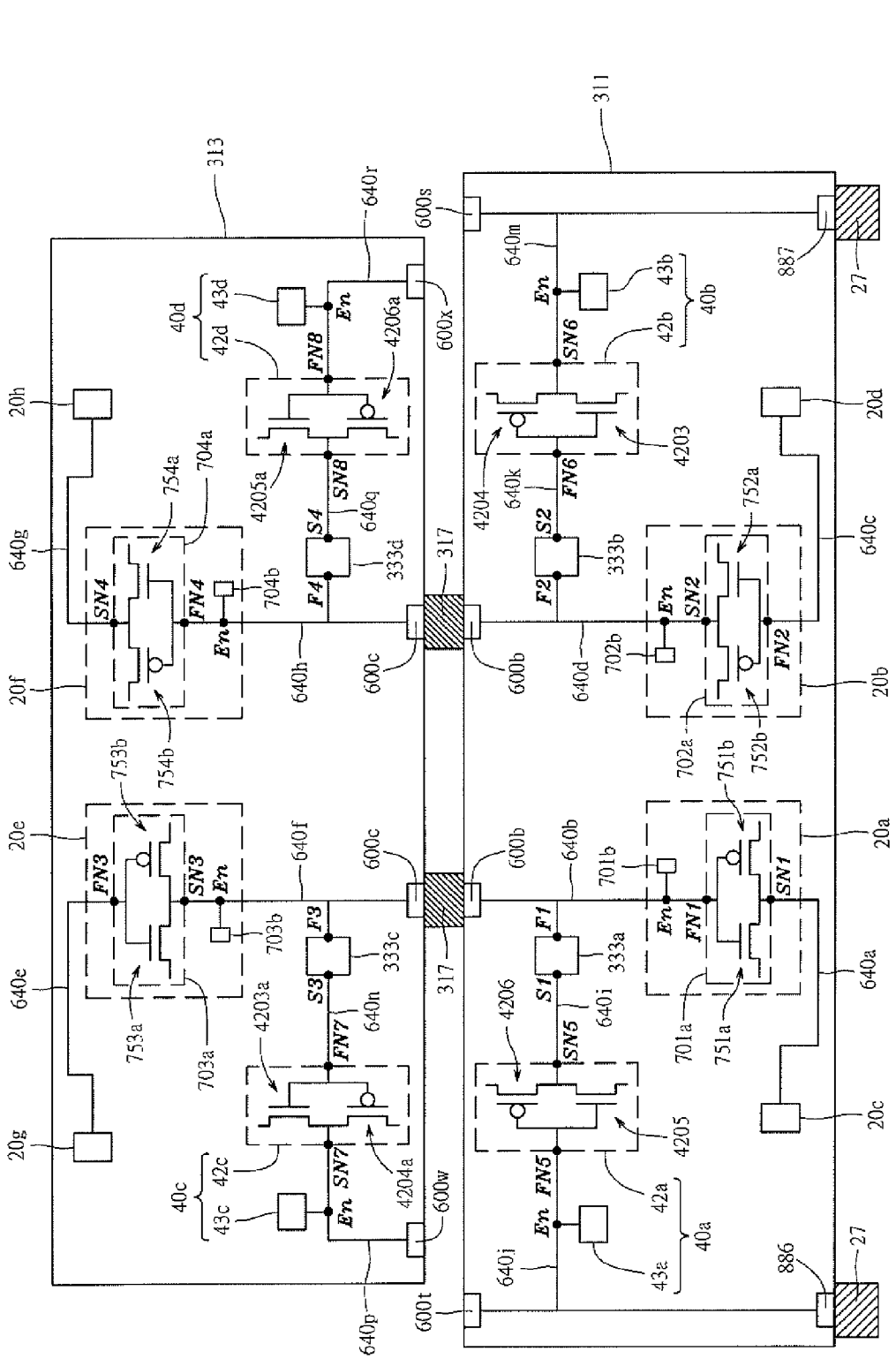

313
311
640r
600s
640m
887
27
40d
43d
42d
FN8
En
4206a
600x
43b
42b
40b
SN6
20h
754a
704a
4205a
SN8
640q
4203
4204
640k
FN6
20d
640g
SN4
FN4
704b
S4
F4
333d
317
S2
F2
333b
752a
640c
754b
640h
600c
600b
640d
702b
En
SN2
FN2
20f
20b
753b
20e
FN3
SN3
En
640f
600c
600b
640b
701b
F3
F1
333a
En
FN1
SN1
20a
640e
753a
703b
333c
317
S3
FN7
640n
S1
SN5
640i
4206
4203a
703a
701a
751a
640a
20g
40c
42c
43c
SN7
4204a
600w
4205
20c
42a
40a
640j
FN5
43a
886
640p
600t

Fig. 39A

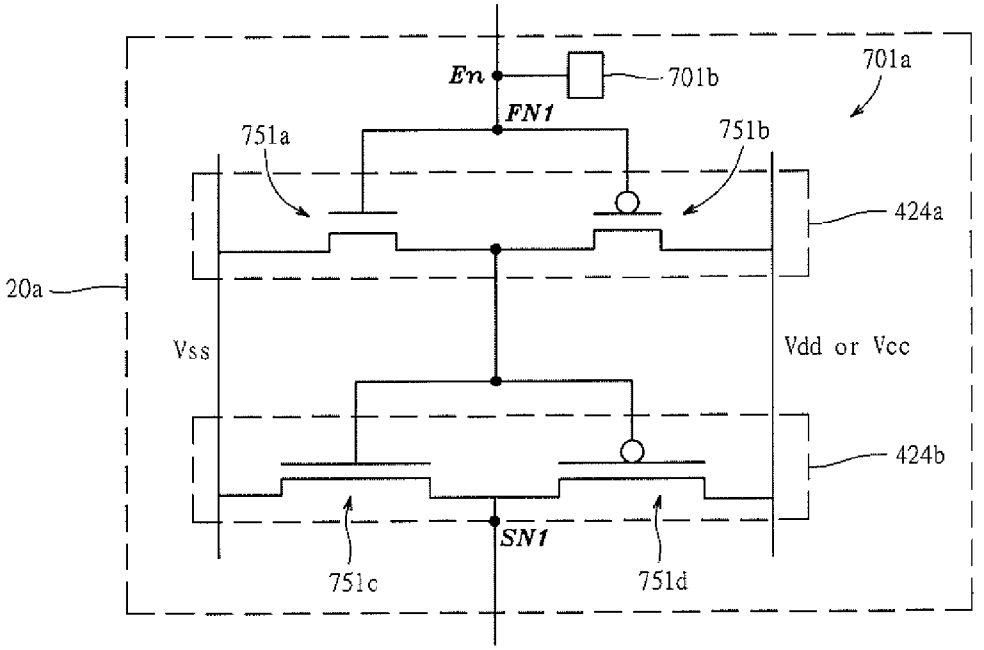


Fig. 39B

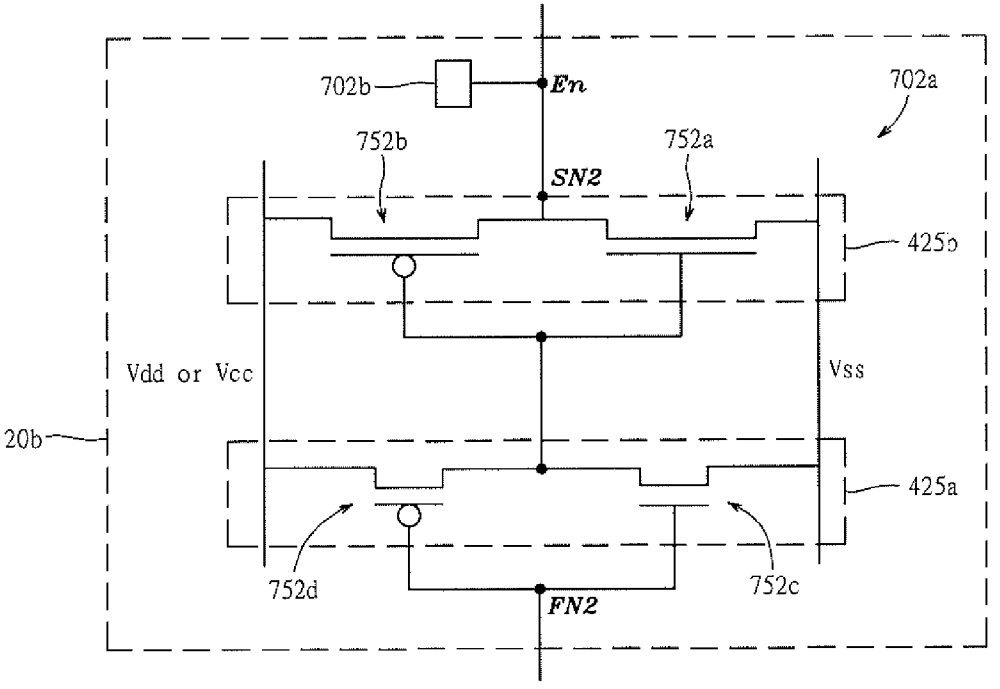


Fig. 39C

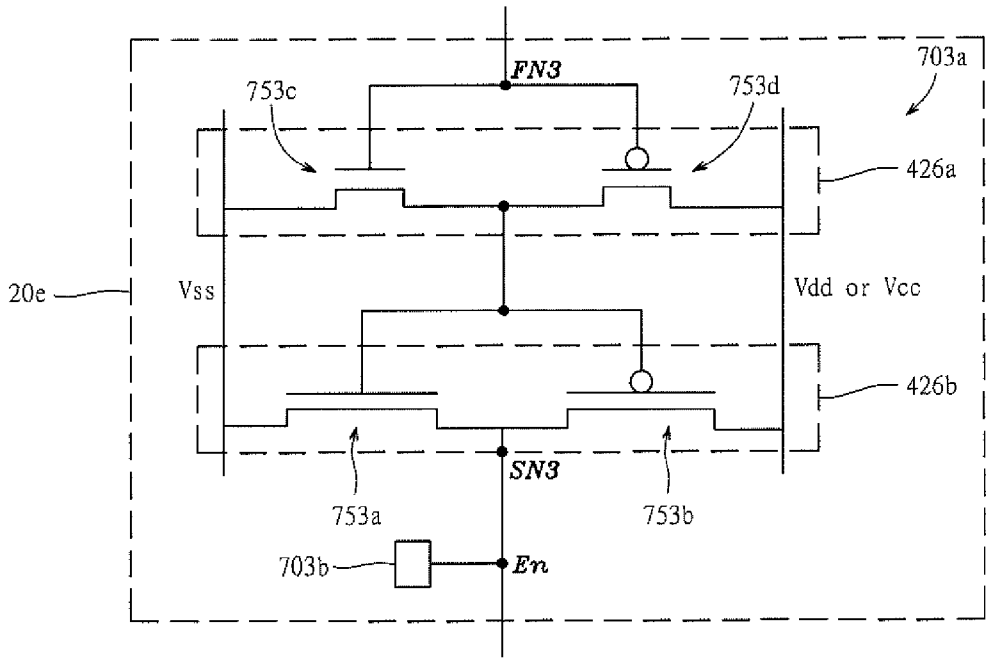


Fig. 39D

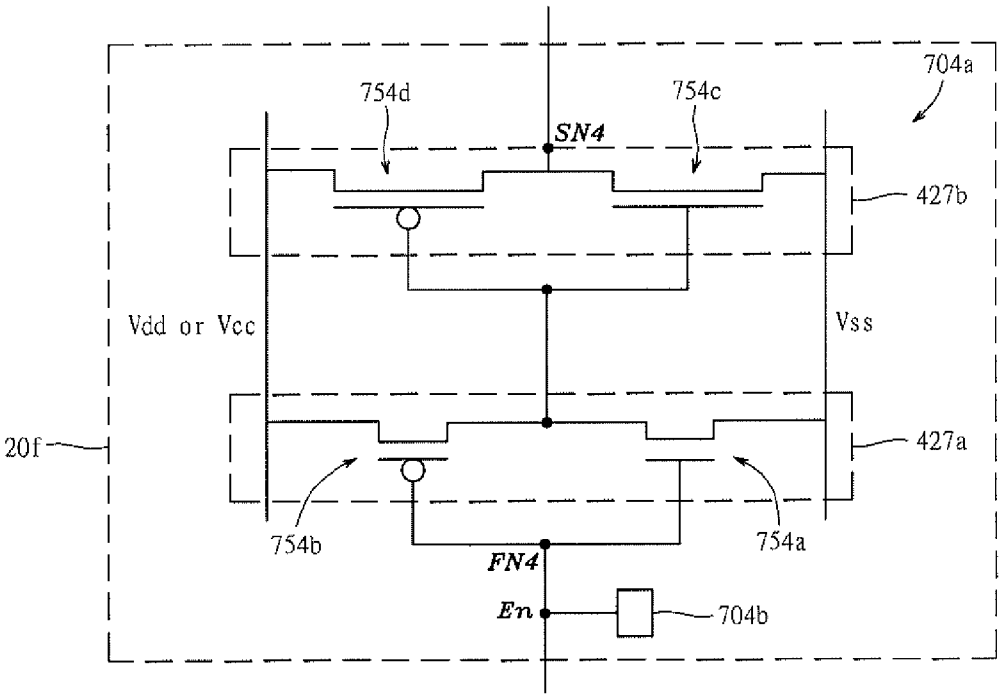


Fig. 39E

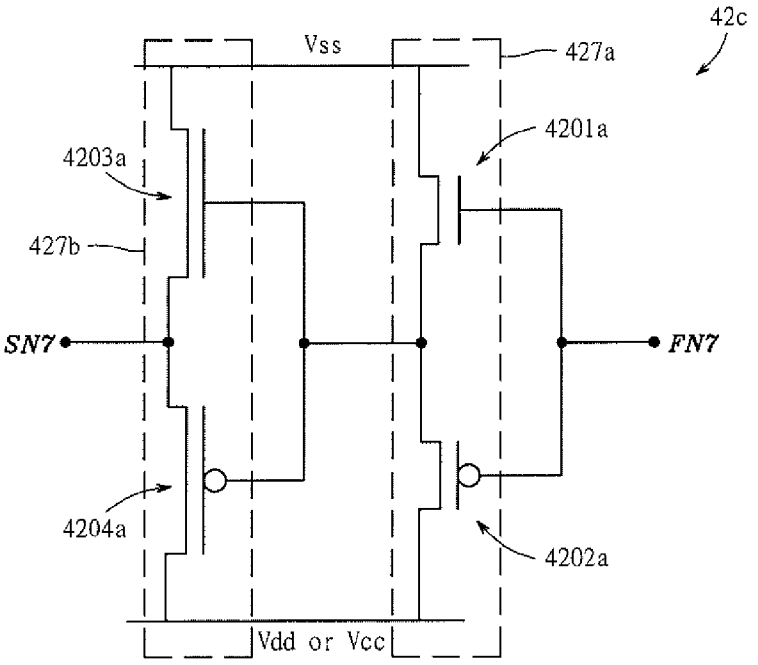


Fig. 39F

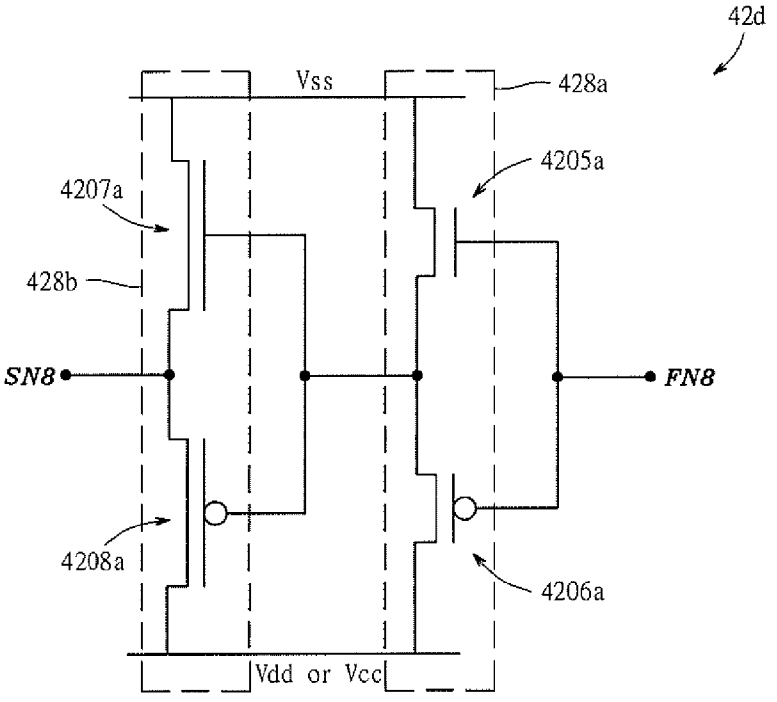


Fig. 39G

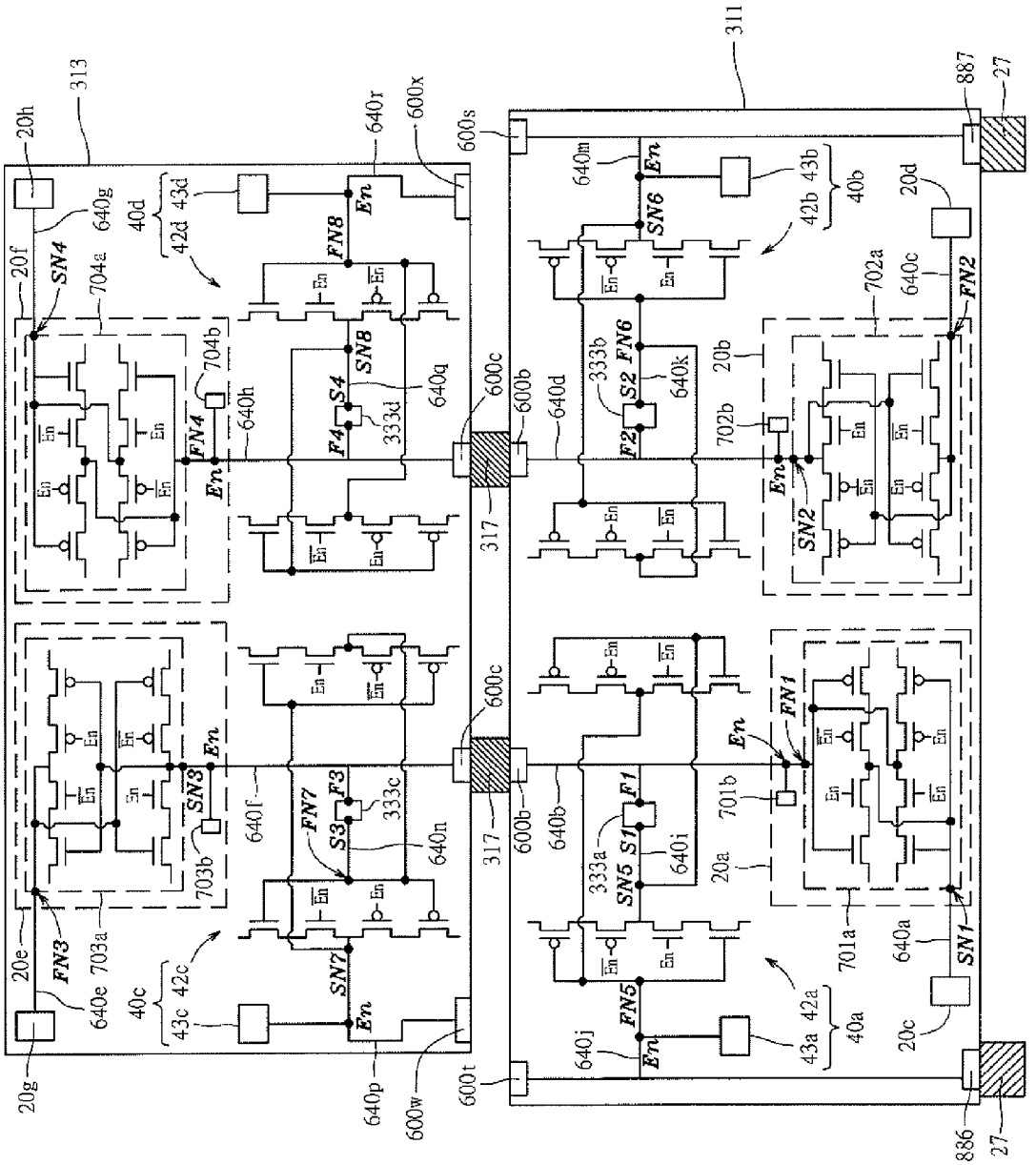

313
311
20h
887
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640r
600x
600s
640m
SN6
En
43b
42b
40b
20d
640g
40d
43d
42d
SN4
20f
704a
FN8
SN8
S4
F4
333d
640q
600c
600b
640d
333b
S2
FN6
640k
20b
702a
640c
FN2
704b
FN4
640h
En
317
F2
702b
SN2
703b
SN3
640f
FN7
S3
F3
333c
640n
FN1
F1
640b
701b
333a
S5
S1
640i
20a
20e
FN3
703a
640e
40c
42c
43c
SN7
640p
600w
600t
640j
FN5
43a
42a
40a
701a
640a
SN1
20c
20g
886

Fig. 39H

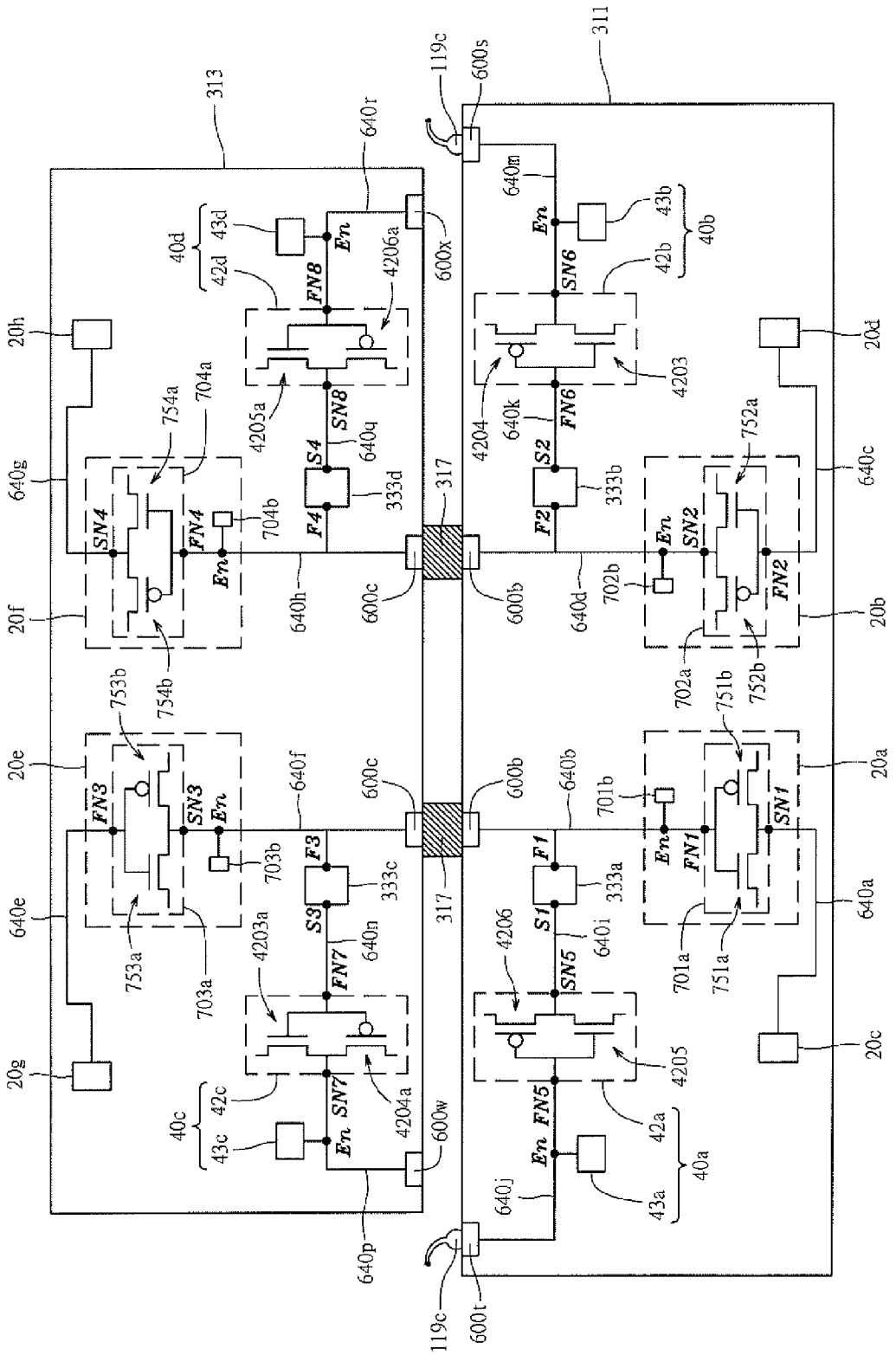

313
311
119c
600s
640r
640m
600x
40d
42d
43d
FN8
En
4206a
4205a
SN8
S4
640q
333d
F4
704b
754a
704a
SN4
FN4
640h
600c
317
600b
640k
FN6
SN6
42b
43b
40b
4203
4204
S2
333b
F2
752a
640c
SN2
FN2
640d
702b
702a
751b
752b
20h
640g
20f
20e
640e
20g
20d
20b
20a
20c
753b
754b
753a
703b
703a
FN3
SN3
640f
F3
333c
S3
640n
FN7
4203a
4204a
600w
40c
42c
43c
SN7
640p
119c
600t
640j
F1
333a
S1
640i
SN5
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4205
FN5
42a
43a
40a
701b
701a
751a
FN1
SN1
640a

Fig. 39I

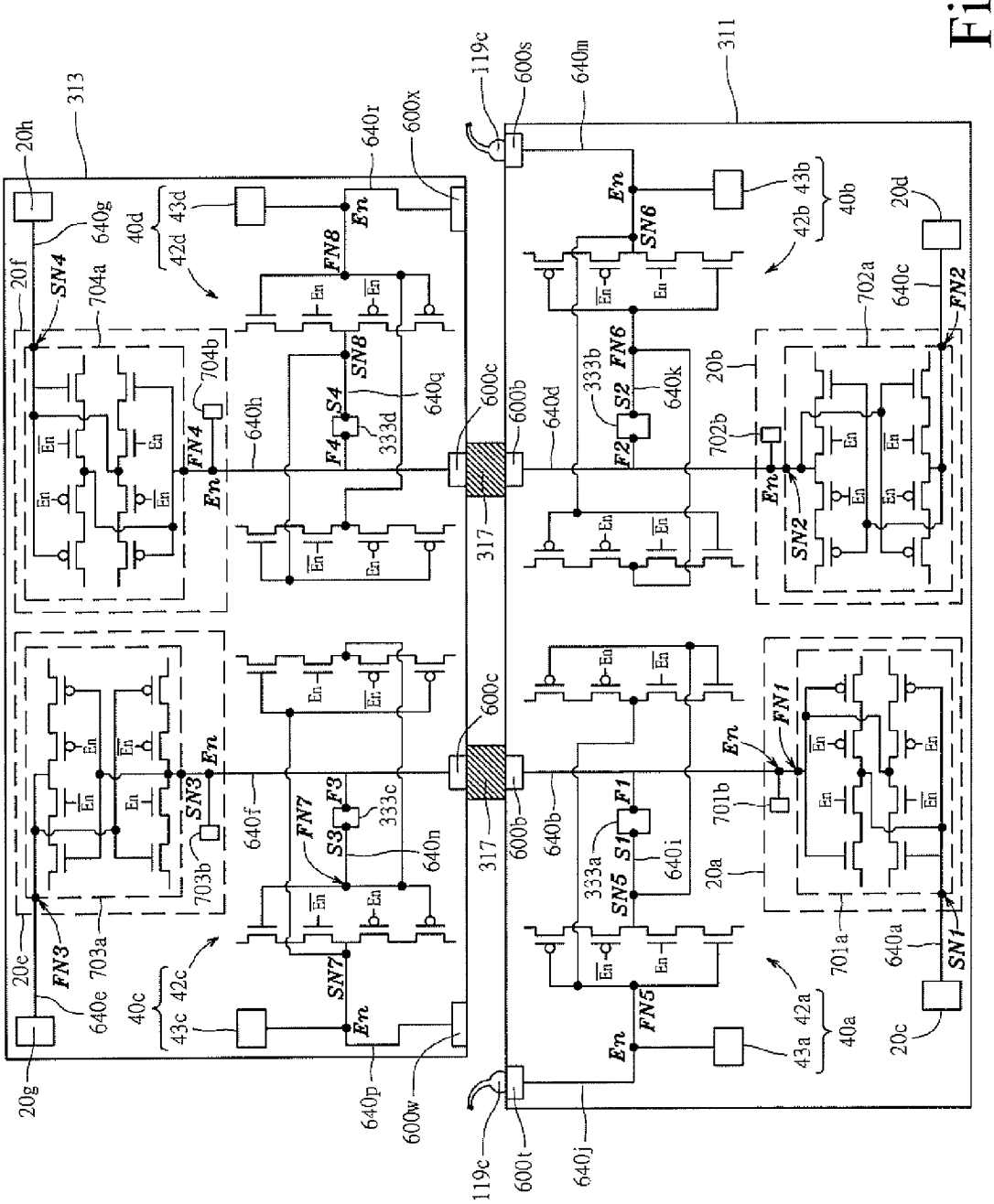

313
311
20h
20f
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20g
20d
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640g
640e
640r
640h
640q
640f
640n
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640w
640m
640d
640b
640j
640k
640i
640a
600x
600s
600c
600b
600t
119c
317
704a
704b
703a
703b
702a
702b
701a
701b
333d
333c
333b
333a
40d
42d
43d
40c
42c
43c
40b
42b
43b
40a
42a
43a
20b
20a
FN8
SN8
S4
F4
FN4
SN4
FN7
SN7
S3
F3
FN3
SN3
FN6
SN6
S2
F2
FN2
SN2
FN5
SN5
S1
F1
FN1
SN1
En

Fig. 39J

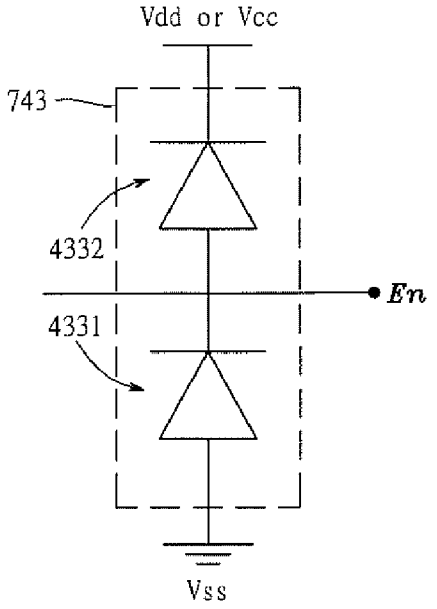


Fig. 40A

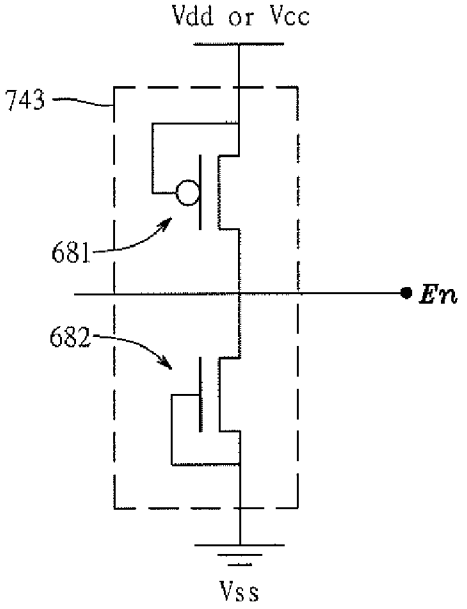


Fig. 40B

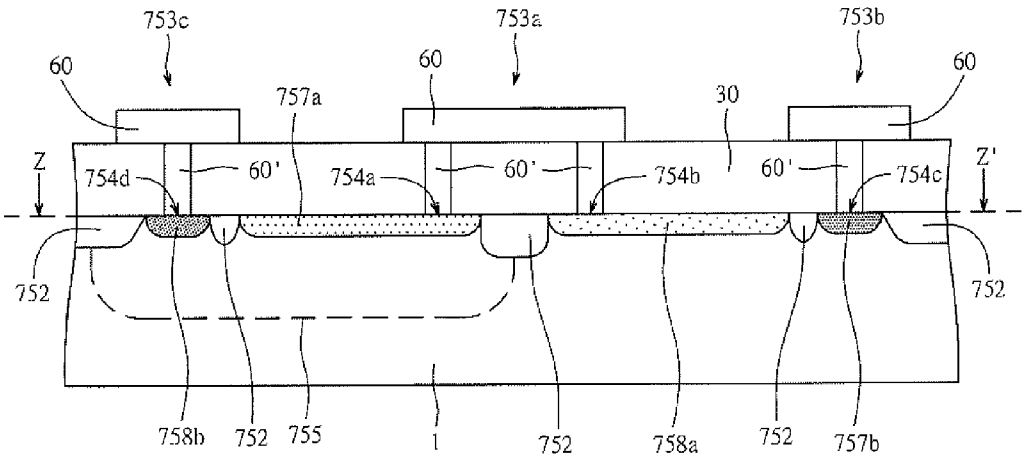


Fig. 40C

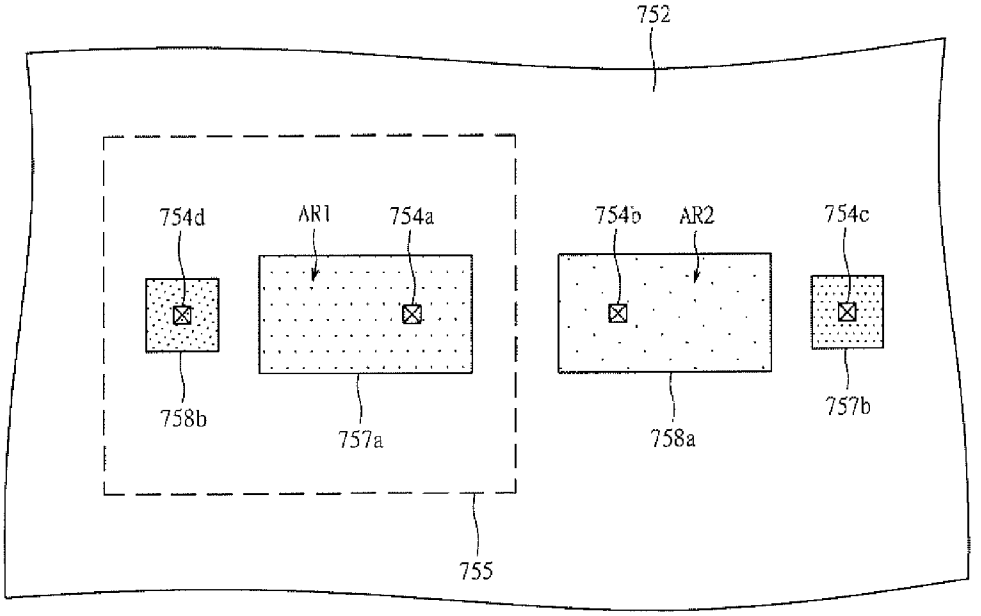


Fig. 40D

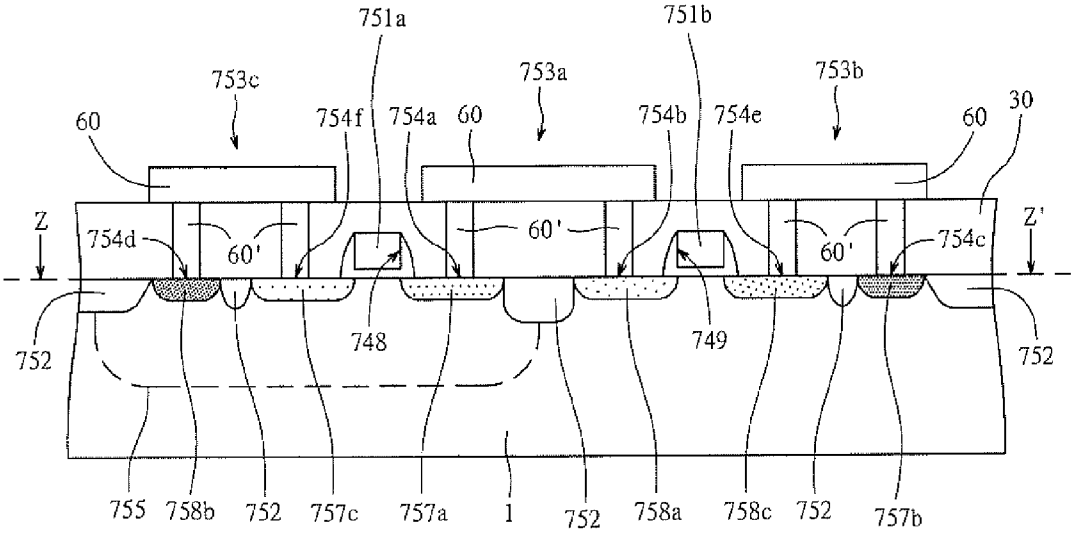


Fig. 40E

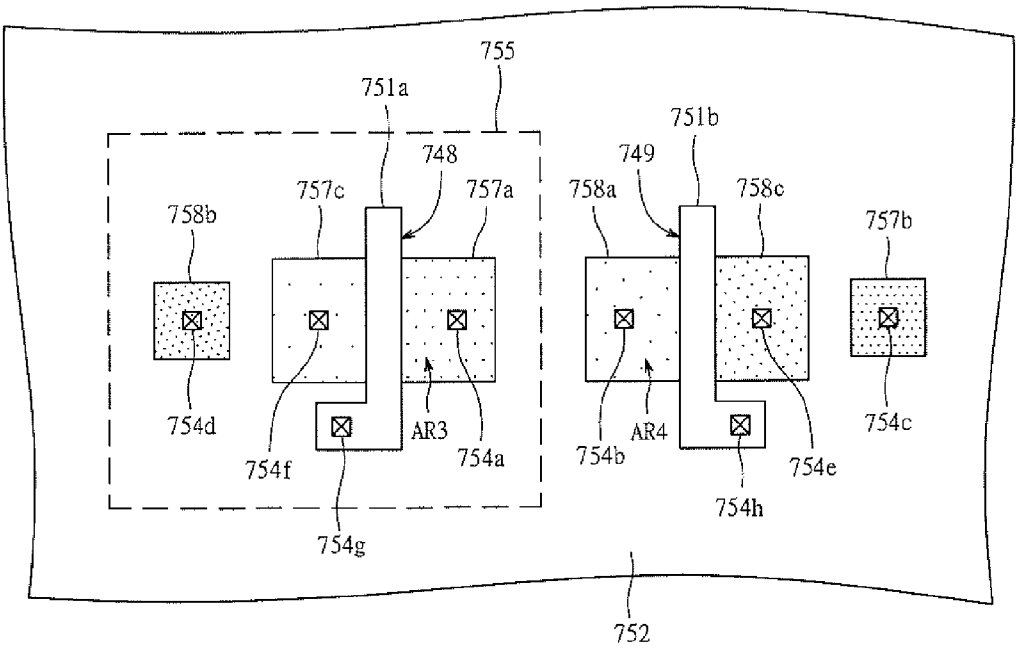


Fig. 40F

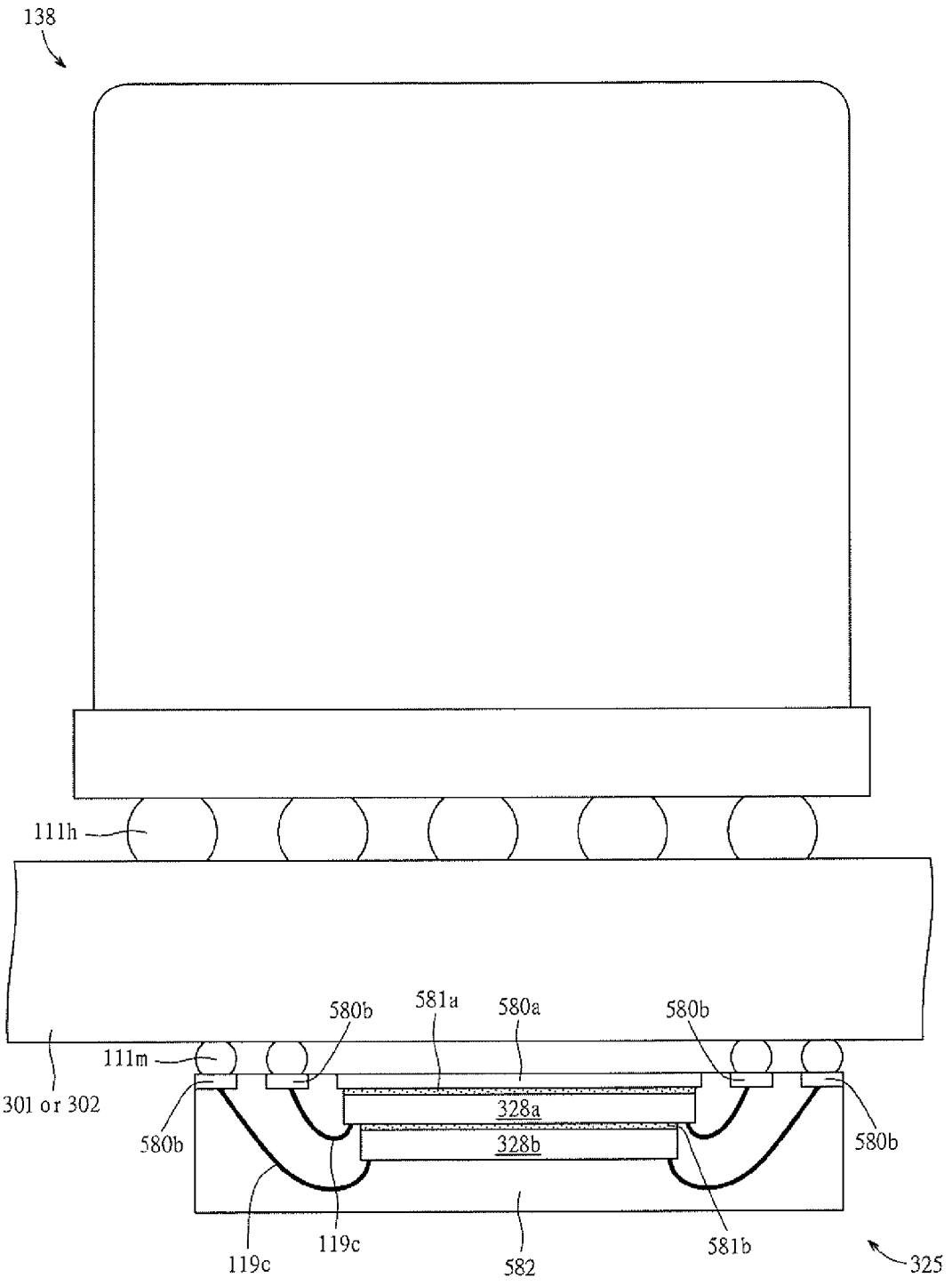

138
111h
580b
581a
580a
580b
111m
301 or 302
580b
328a
328b
580b
119c
119c
582
581b
325

Fig. 41

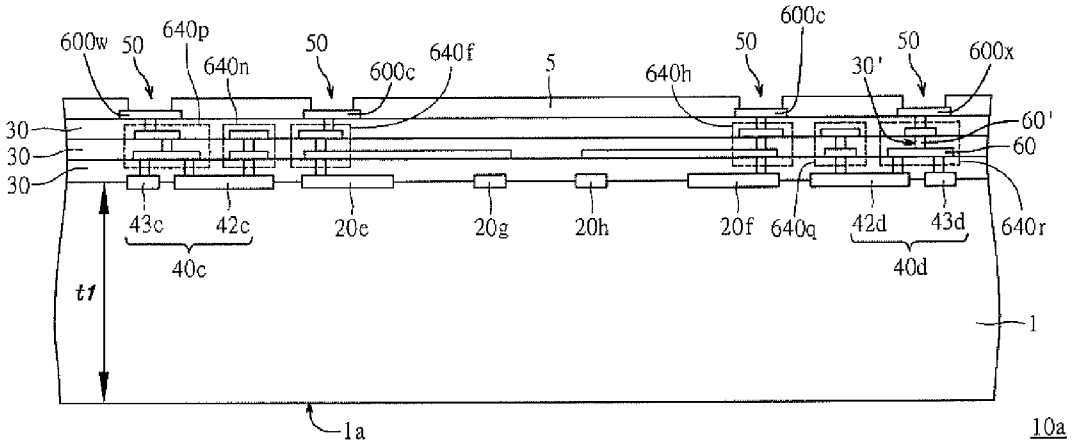


Fig. 42A

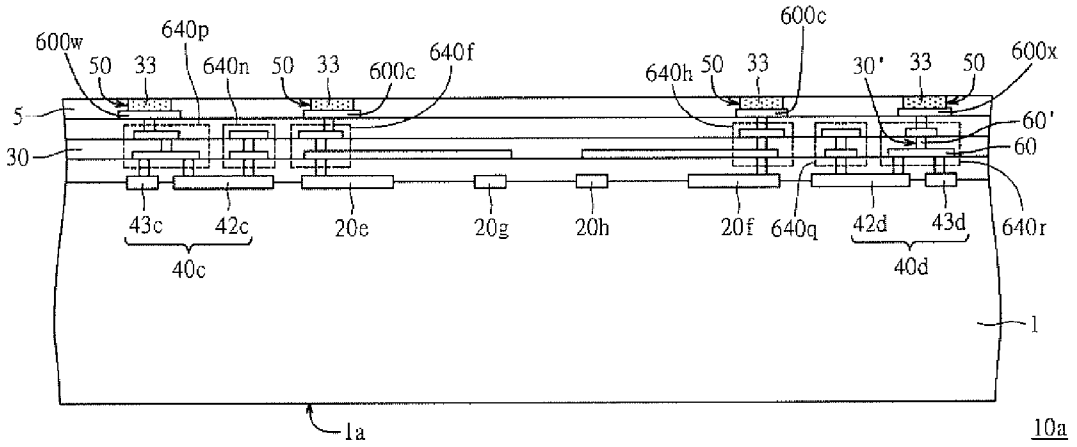


Fig. 42B

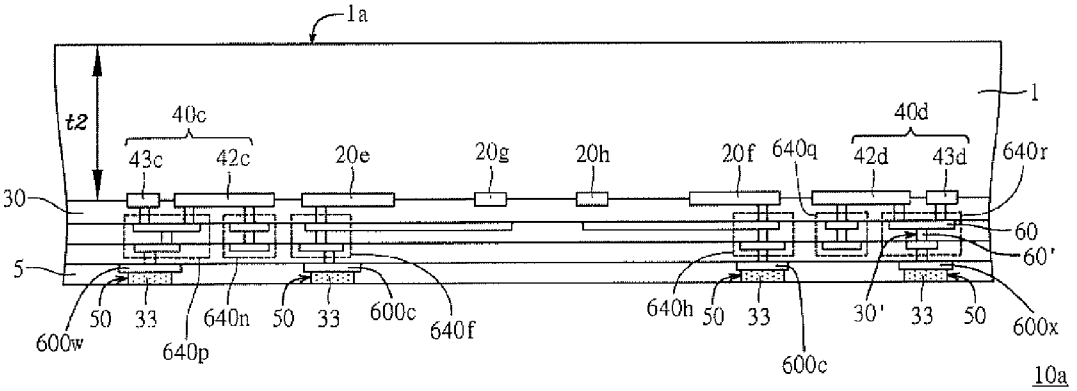


Fig. 42C

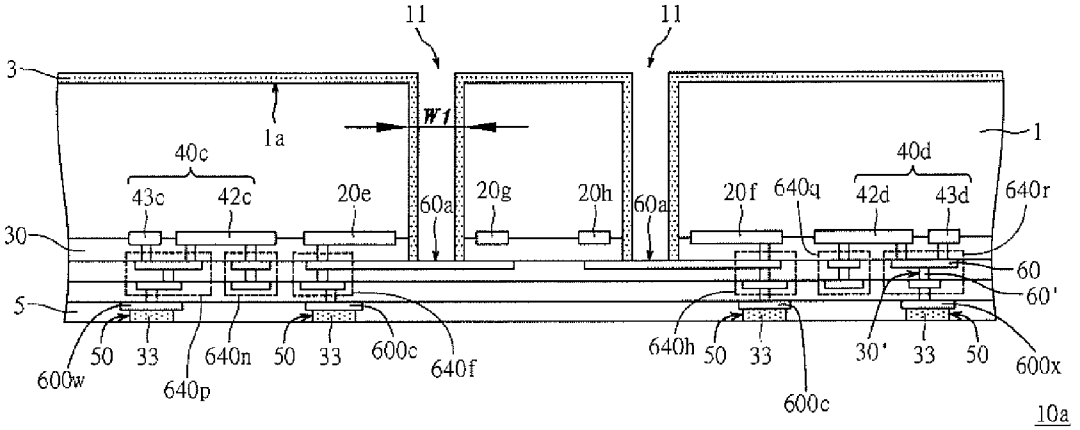


Fig. 42D

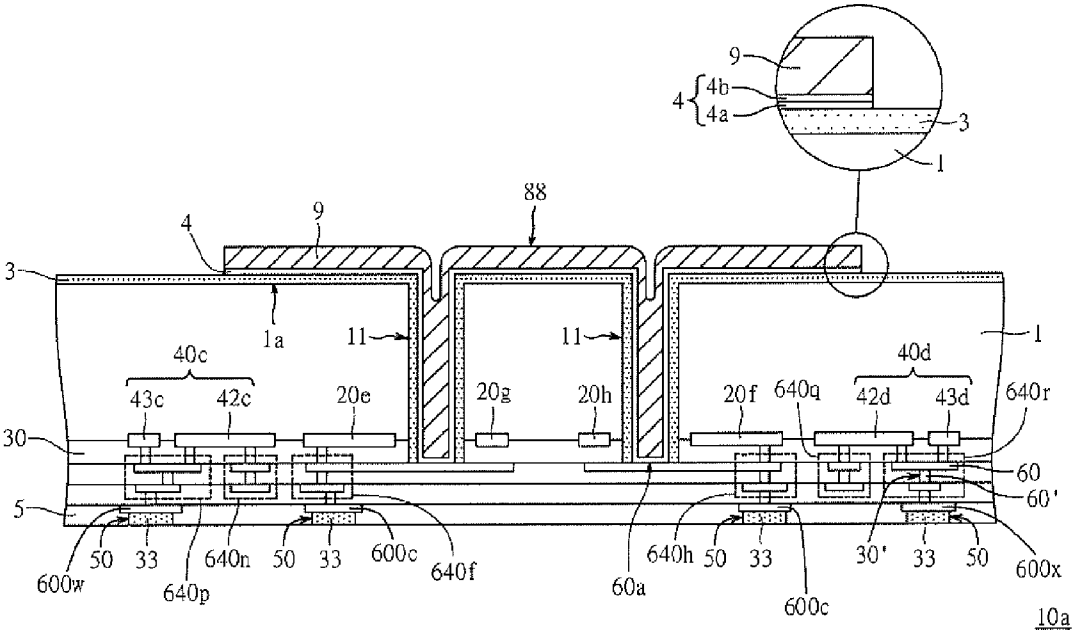


Fig. 42E

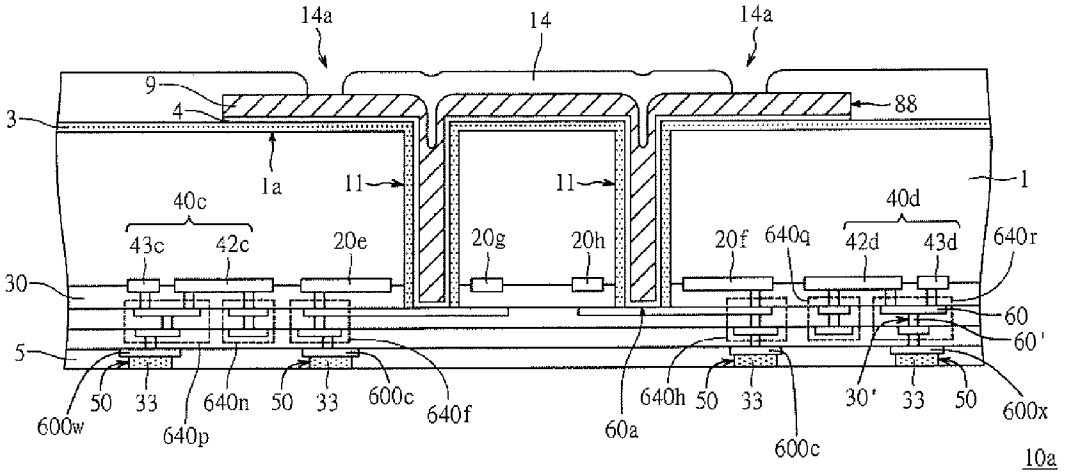


Fig. 42F

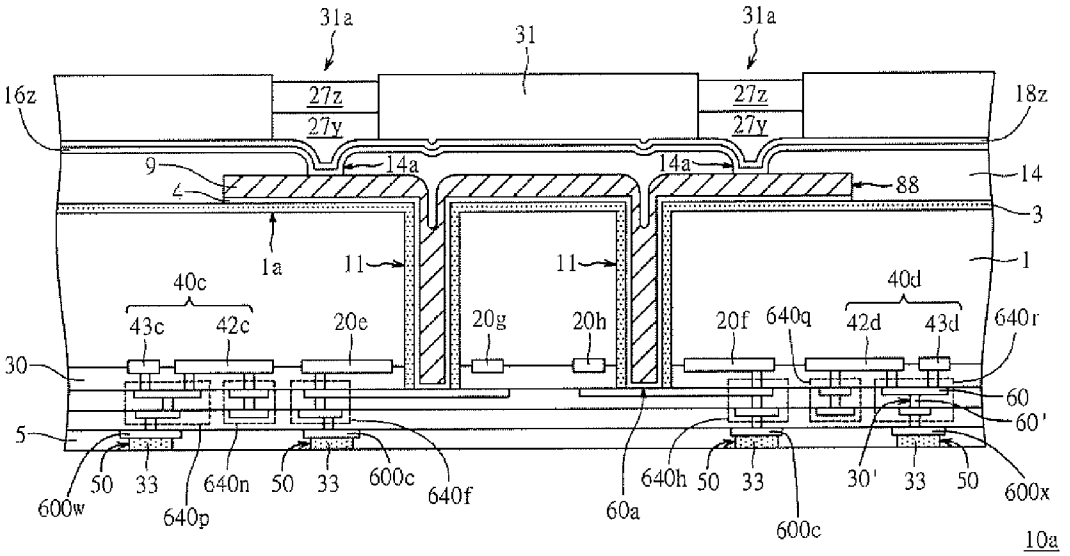


Fig. 42G

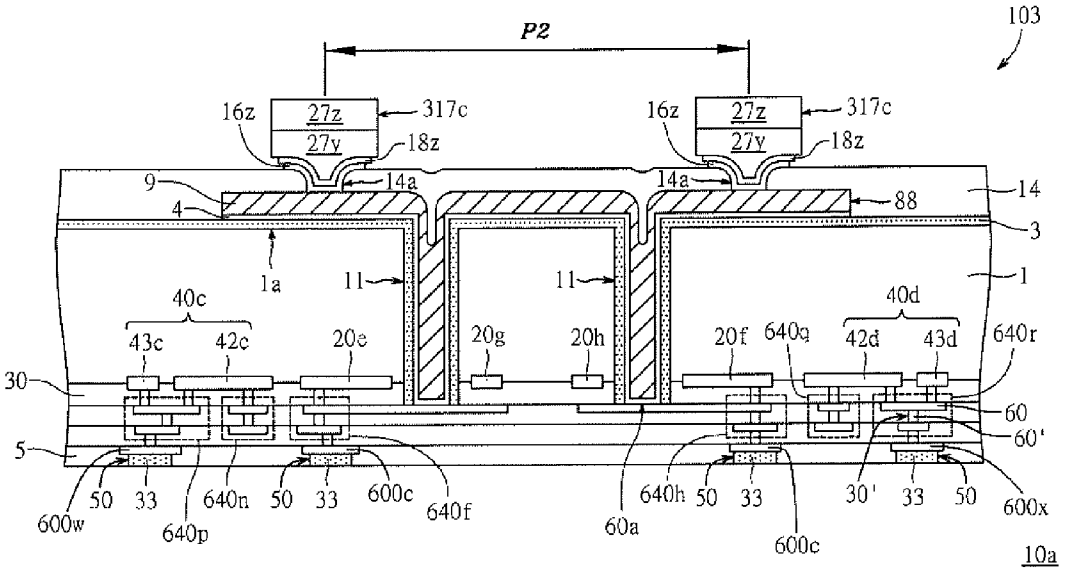


Fig. 42H

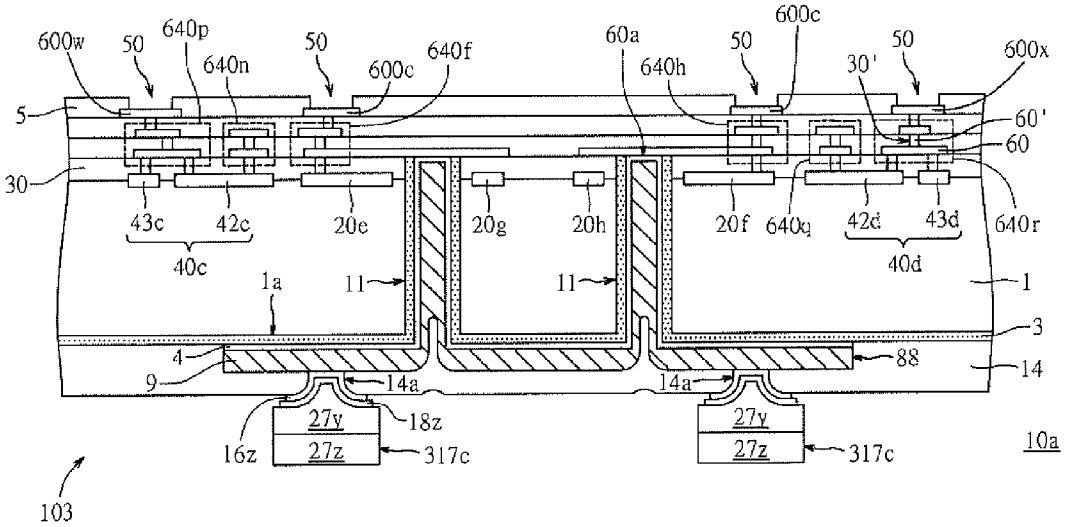


Fig. 42I

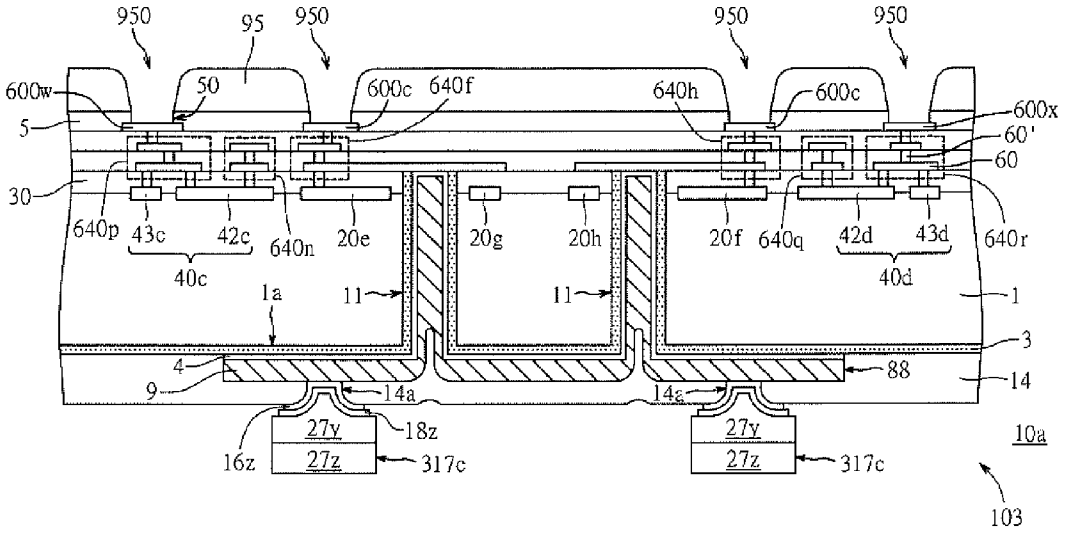


Fig. 42J

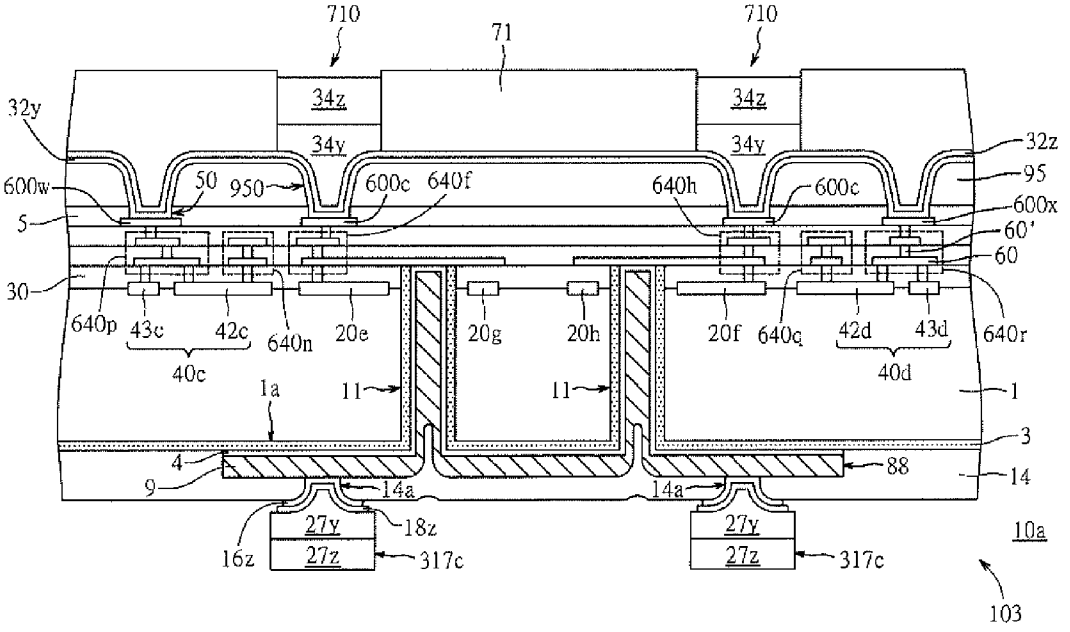


Fig. 42K

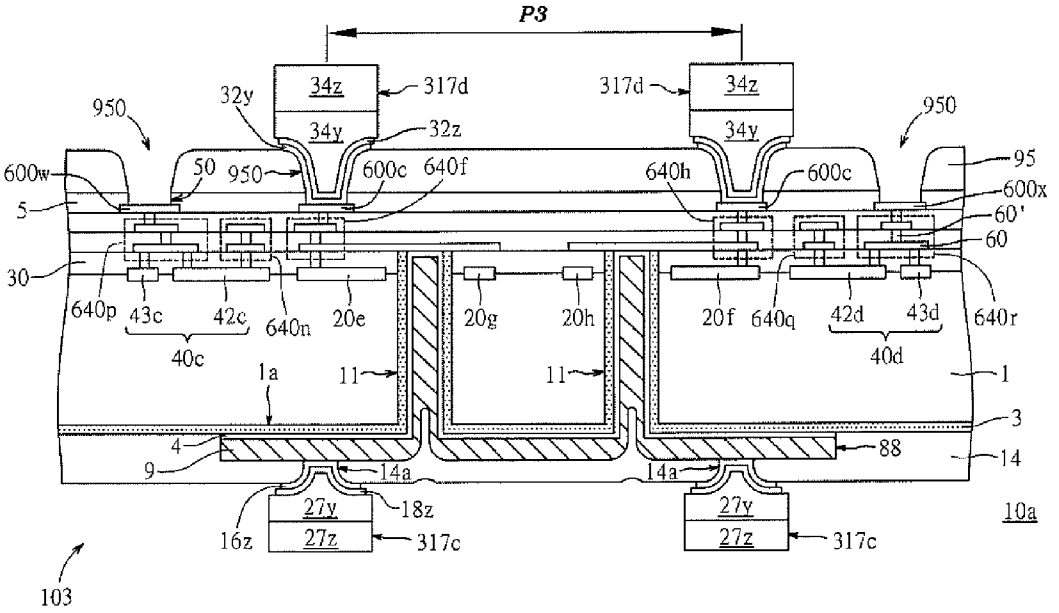


Fig. 42L

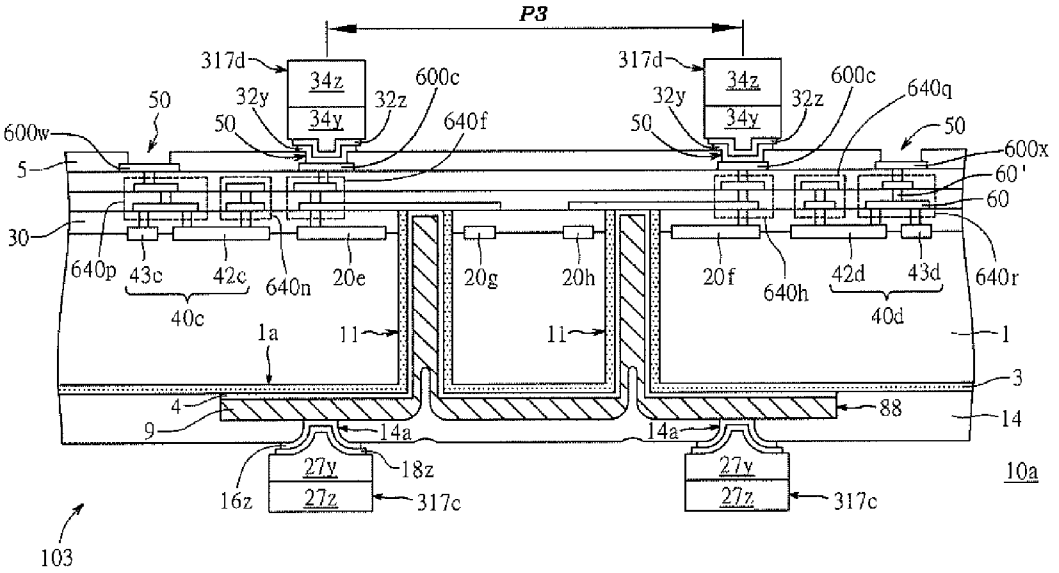


Fig. 42M

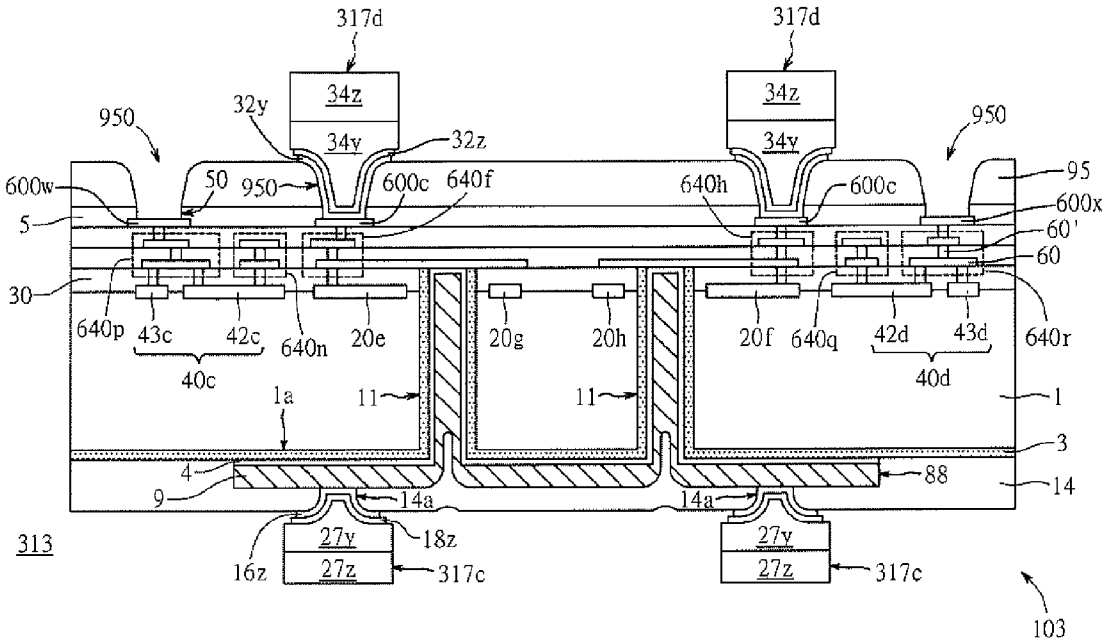


Fig. 42N

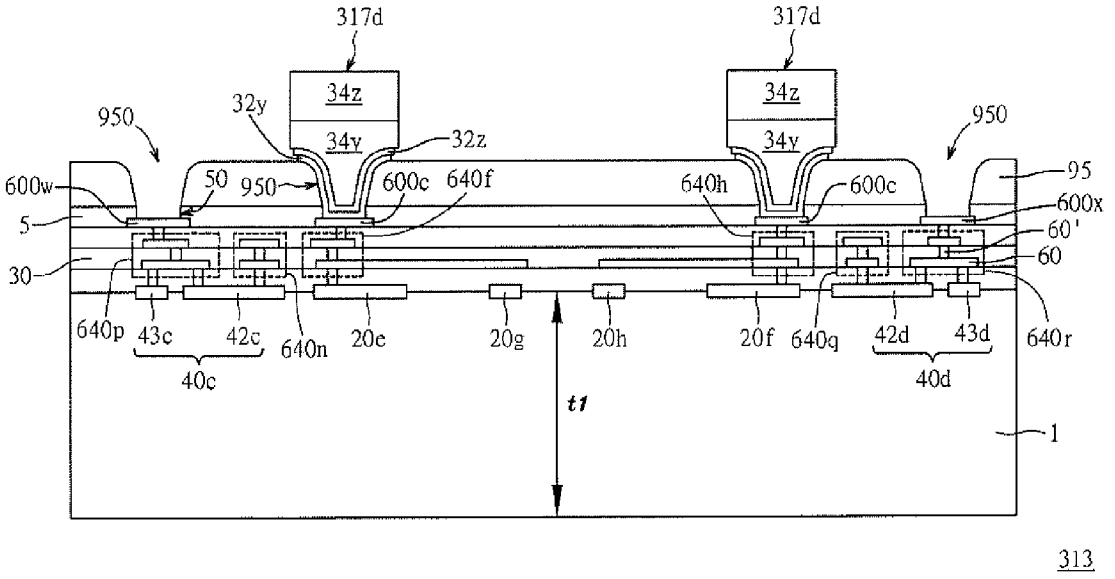


Fig. 42O

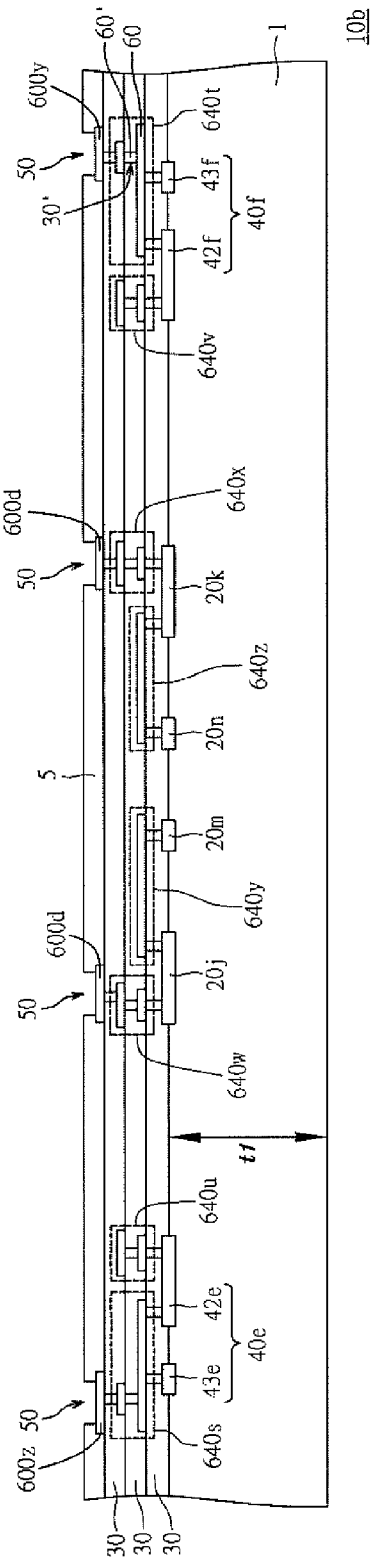


Fig. 43A

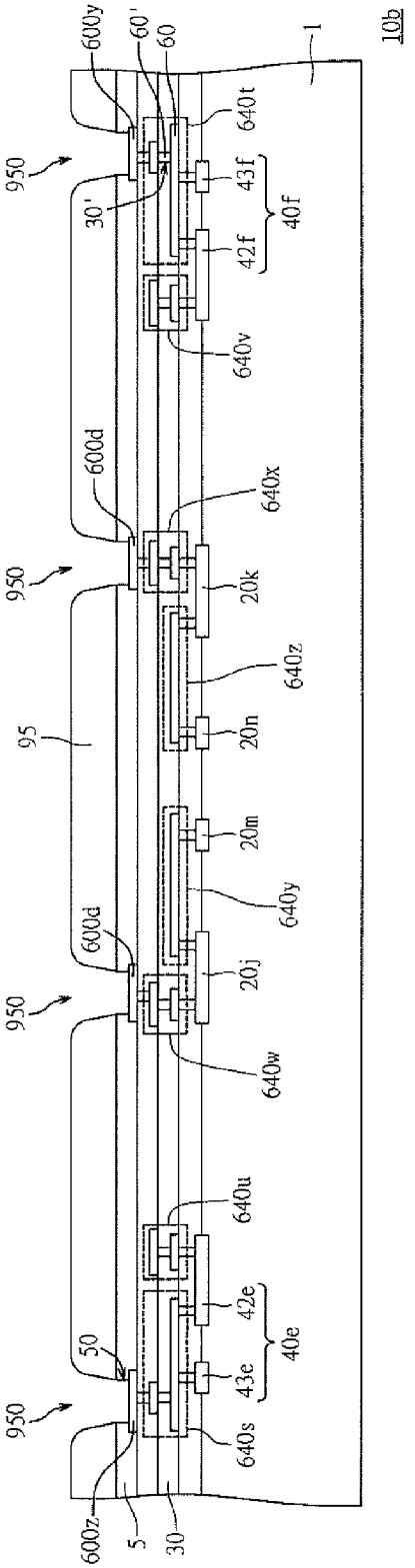


Fig. 43B

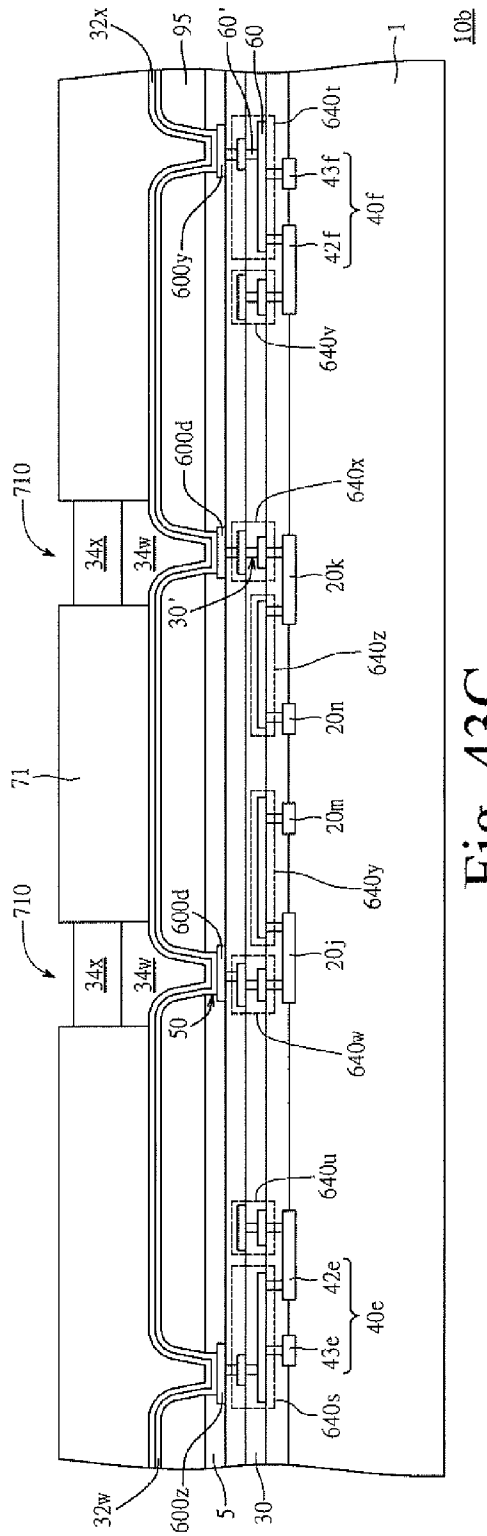


Fig. 43C

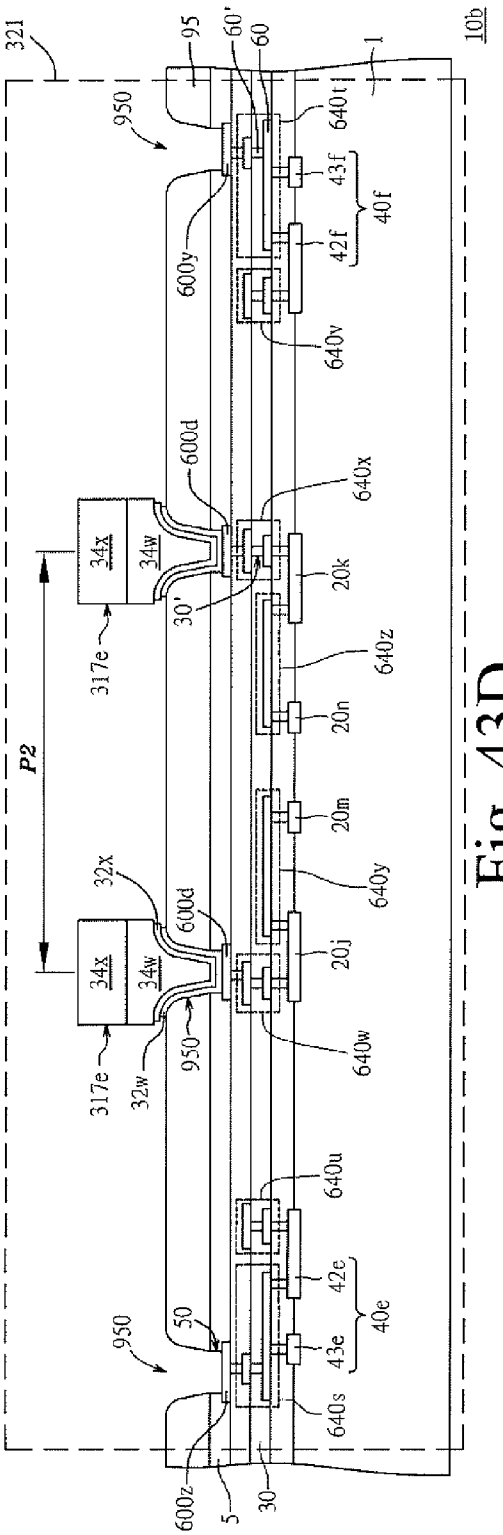


Fig. 43D

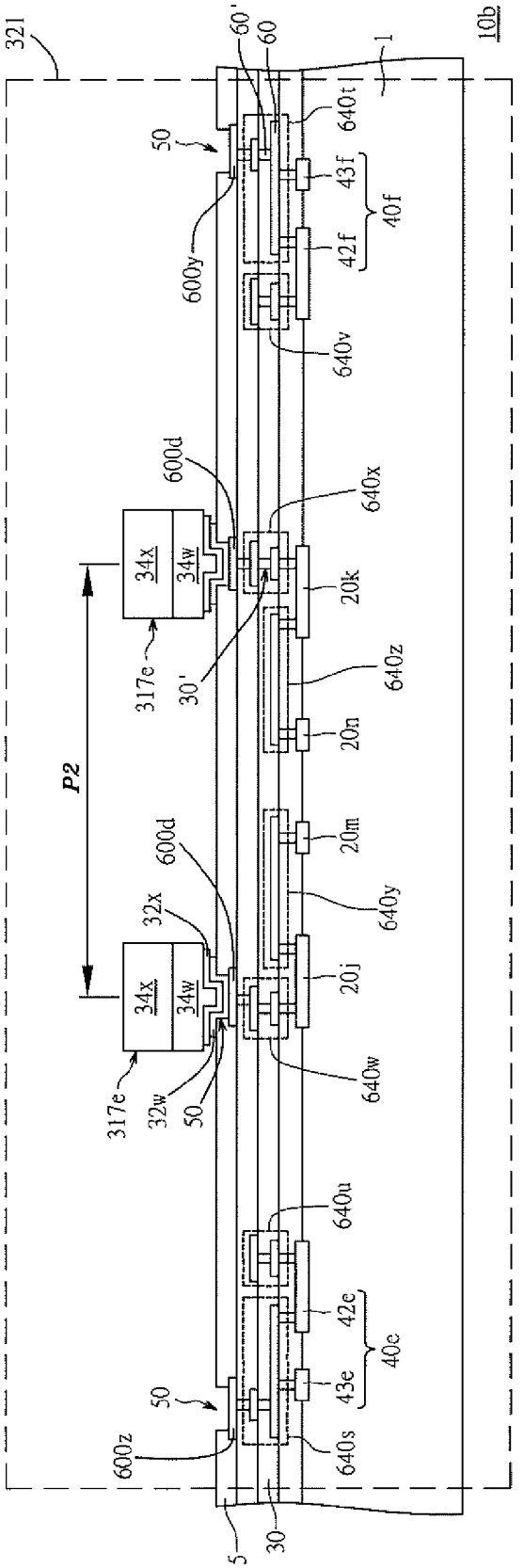

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60'
60
1
10b
50
640f
43f
40f
42f
600y
640v
600d
640x
34x
34w
20k
317e
30'
640z
20n
P2
600d
20m
32x
640y
34x
34w
20j
317e
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50
640w
640u
42e
40e
43e
50
600z
640s
30
5

Fig. 43E

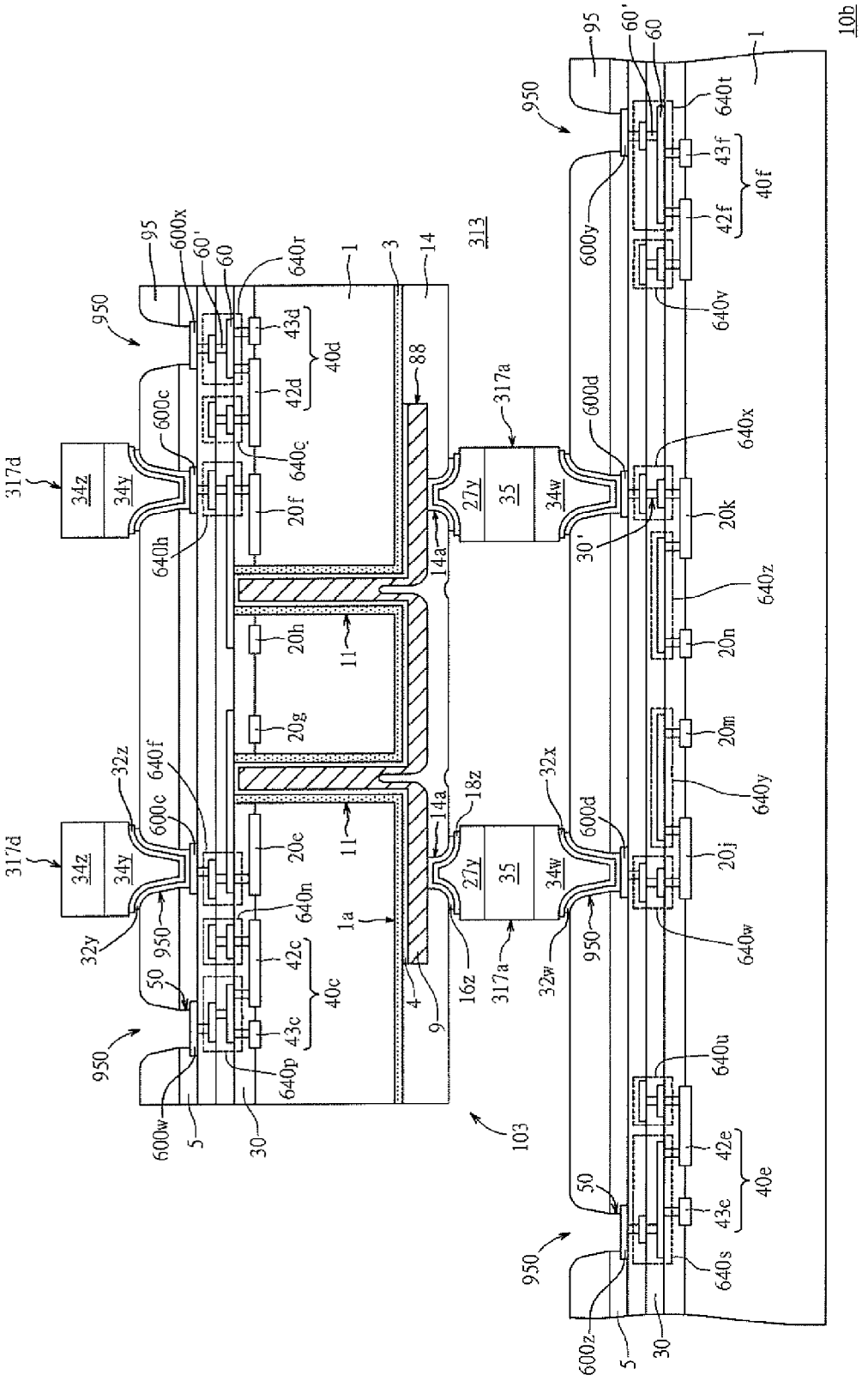

10b
103
313
317a
317d
950
95
60'
60
600x
600'
600c
600d
600y
600w
600z
640r
640t
640v
640x
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640y
640w
640u
640s
640h
640c
640f
640m
640p
1
1a
3
4
5
9
11
14
14a
16z
18z
20c
20d
20e
20f
20g
20h
20j
20k
20m
20n
27y
30
30'
32x
32y
32z
32w
34w
34y
34z
35
40c
40d
40e
40f
42c
42d
42e
42f
43c
43d
43e
43f
50
88

Fig. 44A

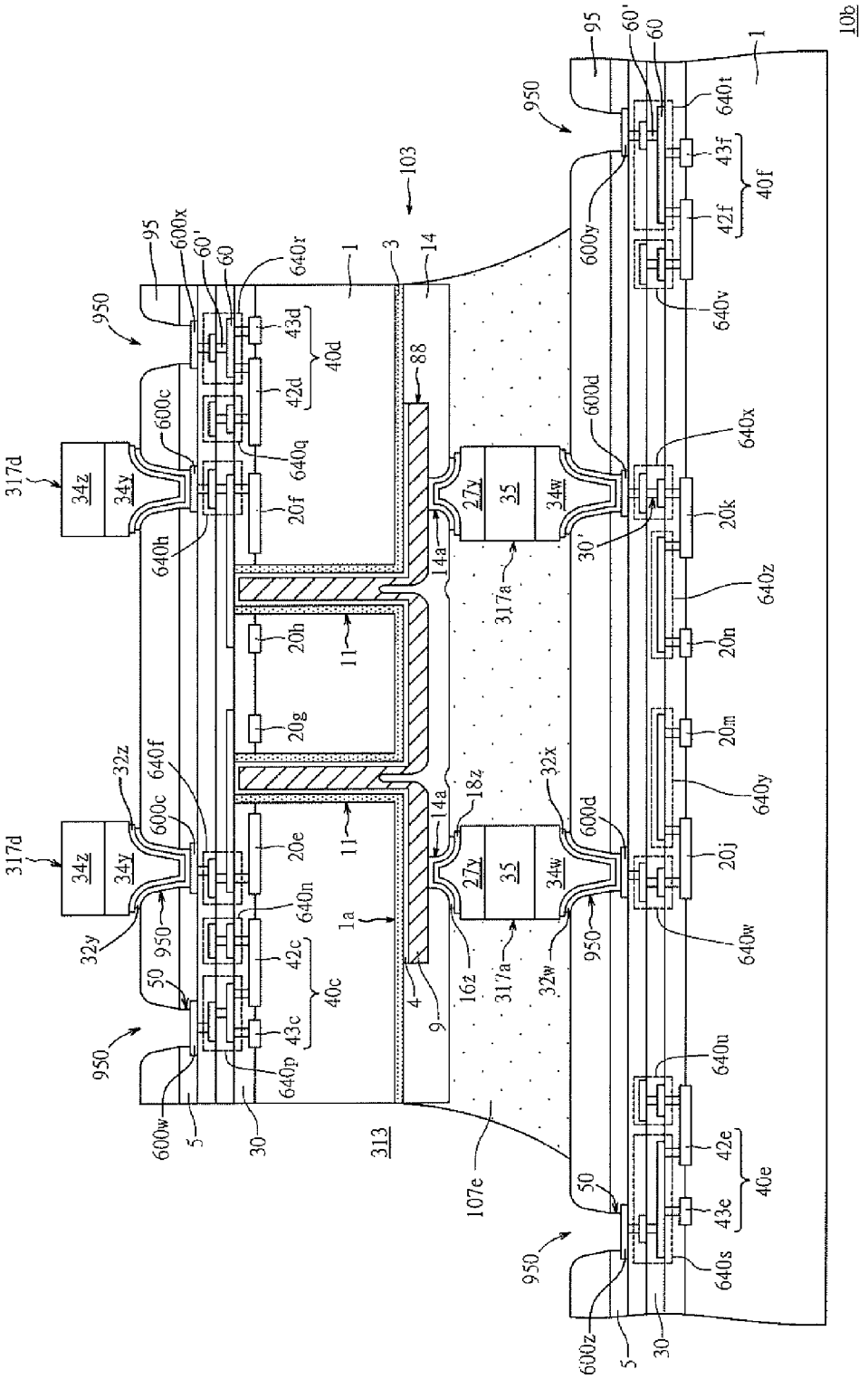

10b
1
95
60'
60
640t
43f
42f
40f
640v
600y
950
103
3
14
640r
600x
43d
42d
40d
88
600d
640x
317d
34z
34y
600c
640q
20f
27y
35
34w
20k
30'
14a
317a
640h
20h
11
640z
20n
20g
32z
640f
18z
32x
20e
20m
640y
20j
640w
1a
42c
40c
43c
640p
640n
42e
40e
43e
640s
600w
600z
5
30
313
107e
50
4
9
16z
32w
32y

Fig. 44B

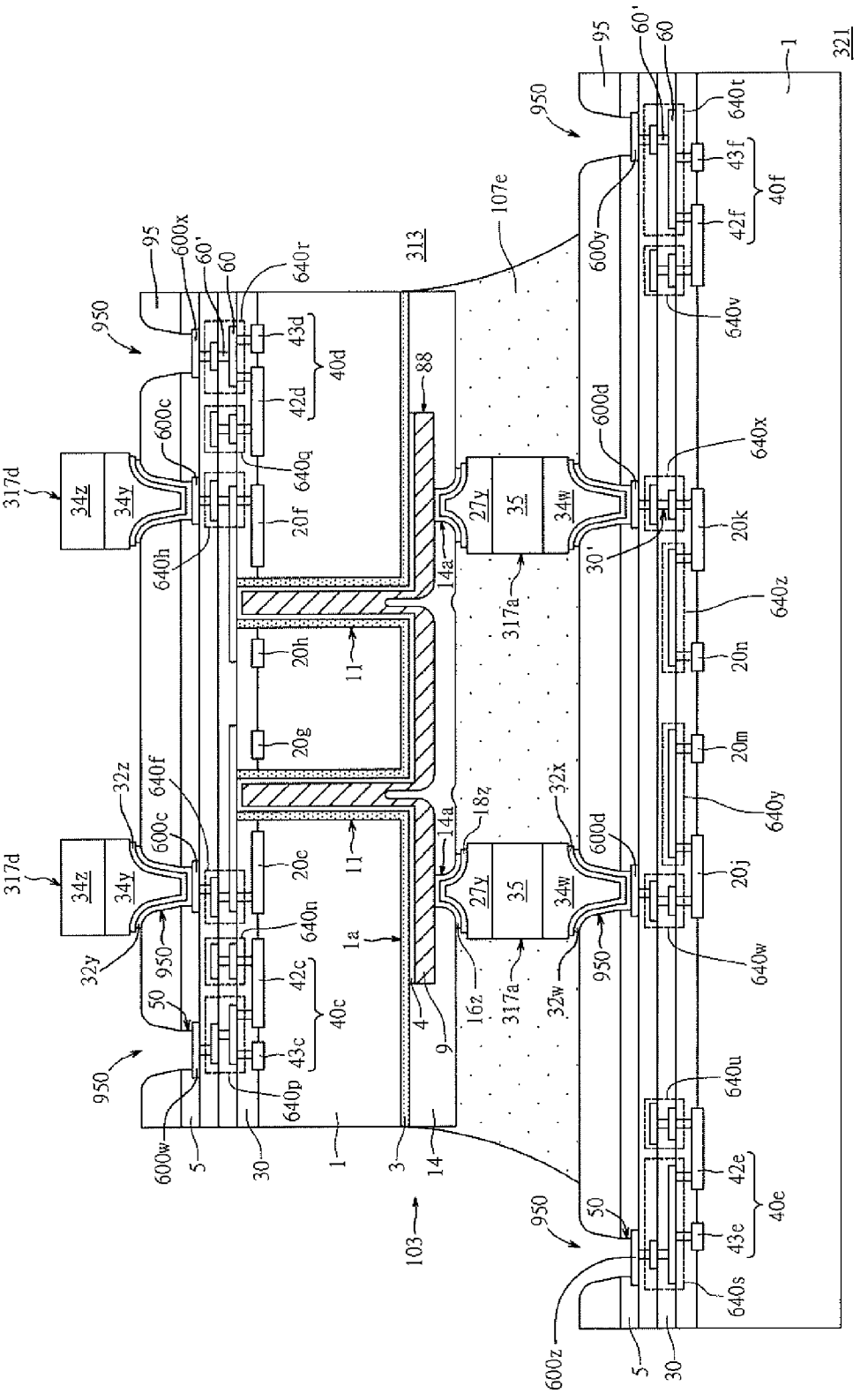

95
600x
60'
60
640r
313
107e
950
88
600c
317d
34z
34y
640h
20f
640q
43d
42d
40d
20h
20g
11
14a
27y
35
34w
317a
600y
600d
640x
20k
30'
640z
20n
20m
640y
20j
640w
640u
42e
40e
43e
640s
600z
5
30
640t
43f
42f
40f
640v
321
1
32z
640f
18z
32x
32y
50
20c
640n
42c
40c
43c
640p
1a
4
9
16z
32w
600w
3
14
103

Fig. 44C

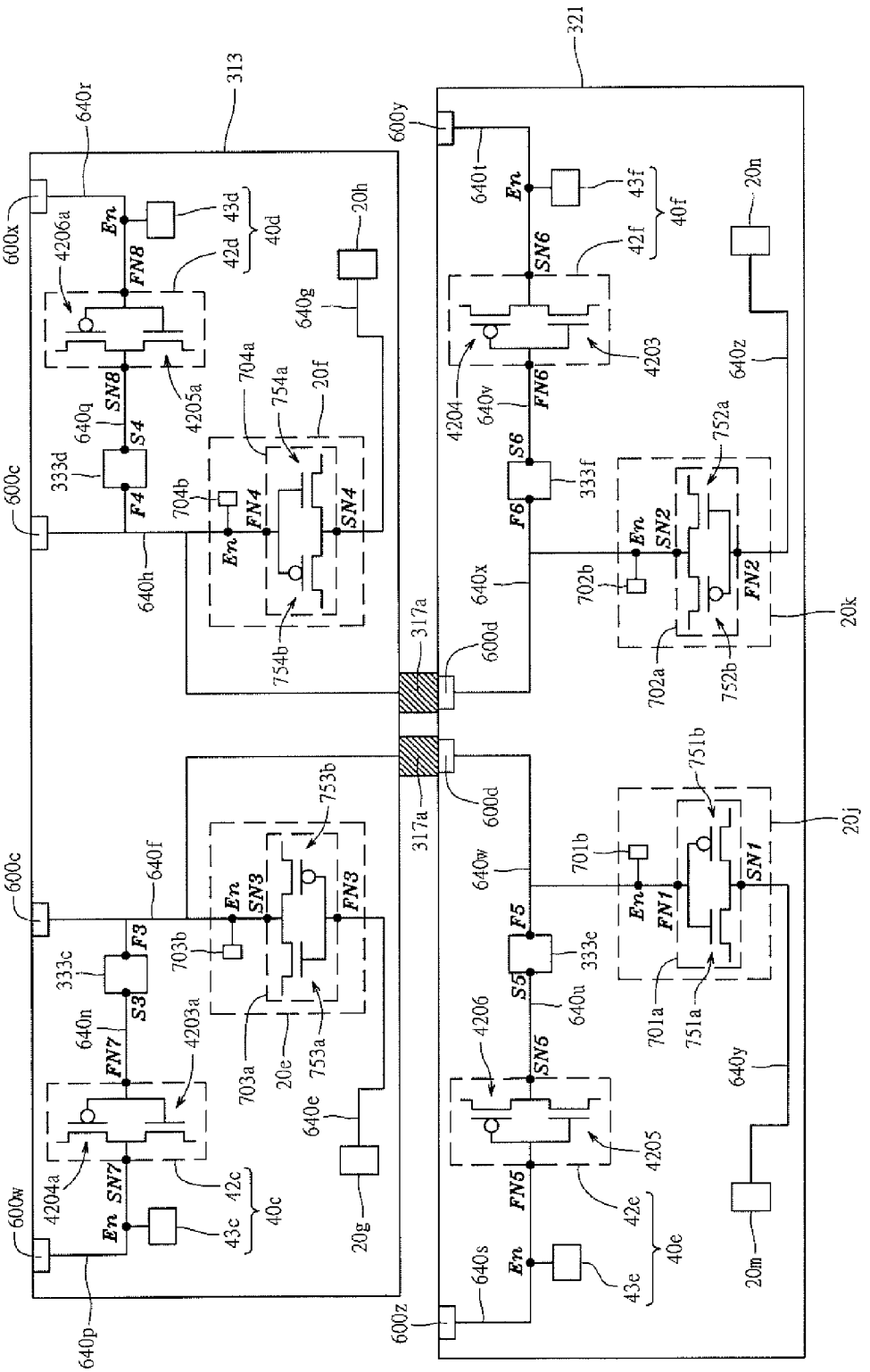

313
321
600x
600y
600c
600w
600z
600d
640r
640t
640q
640v
640x
640n
640u
640w
640y
640p
640s
640h
640f
640g
640z
317a
4206a
4204
4203
4205a
4204a
4206
4205
333d
333f
333c
333e
704a
704b
754a
754b
753b
753a
703a
703b
20e
752a
752b
702a
702b
751b
751a
701a
701b
20f
20h
20k
20j
20n
20g
20m
40d
40f
40c
40e
42d
43d
42f
43f
42c
43c
42e
43e
F4
S4
SN8
FN8
F6
S6
SN6
FN6
F3
S3
SN7
FN7
F5
S5
SN5
FN5
SN4
FN4
SN3
FN3
SN2
FN2
SN1
FN1
En

Fig. 45A

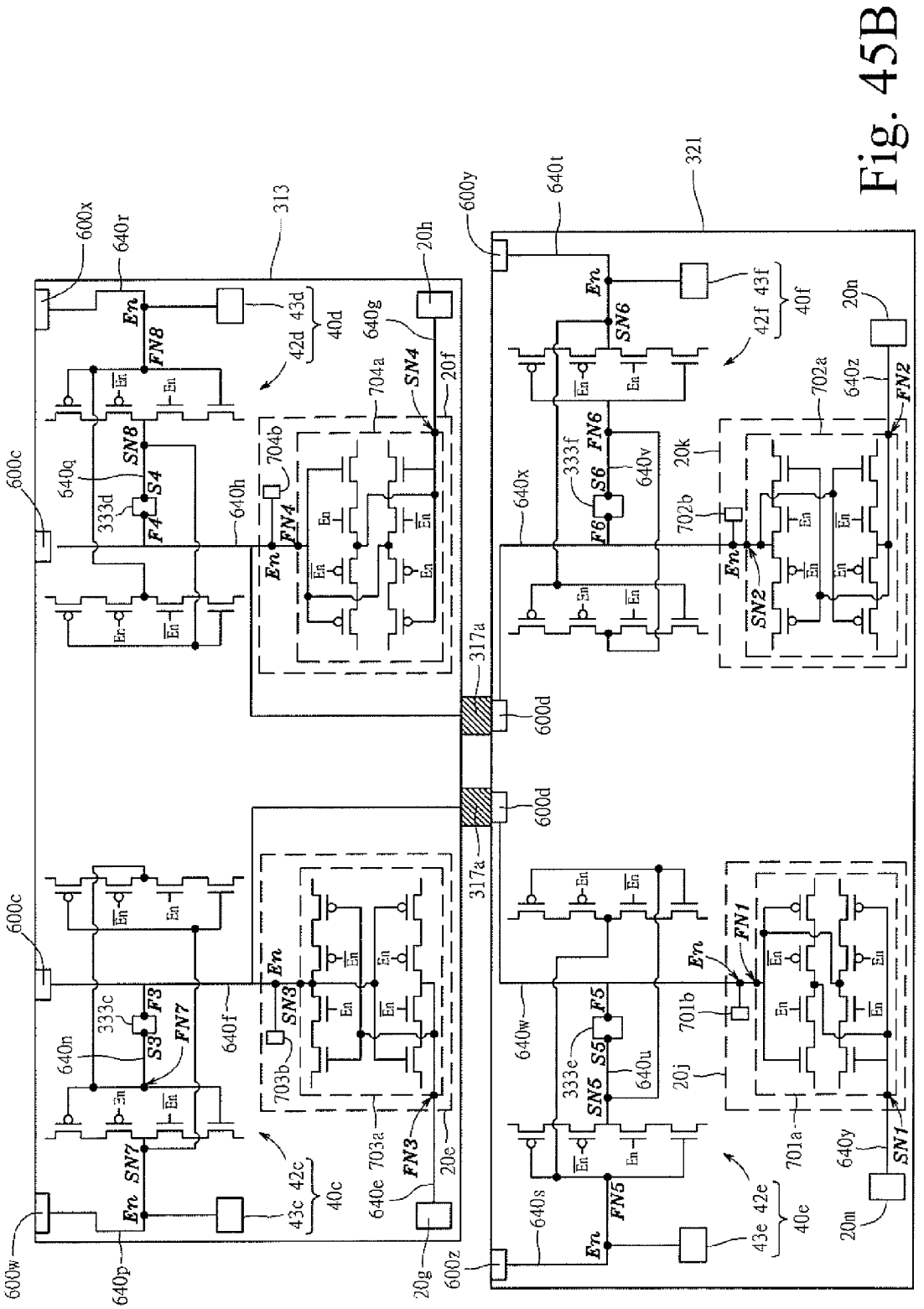


Fig. 45B

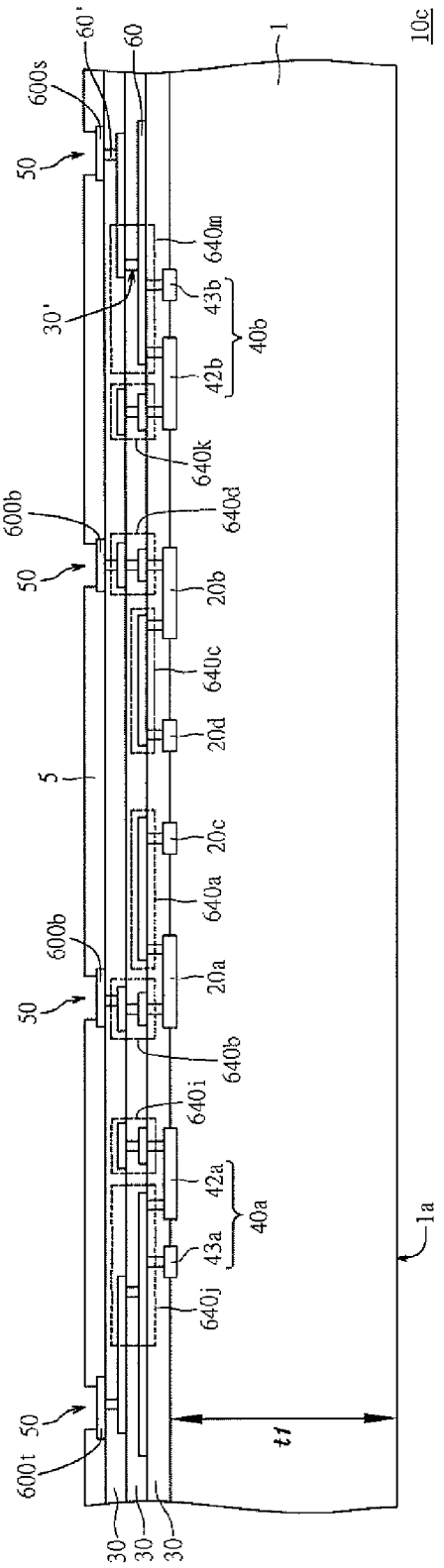


Fig. 46A

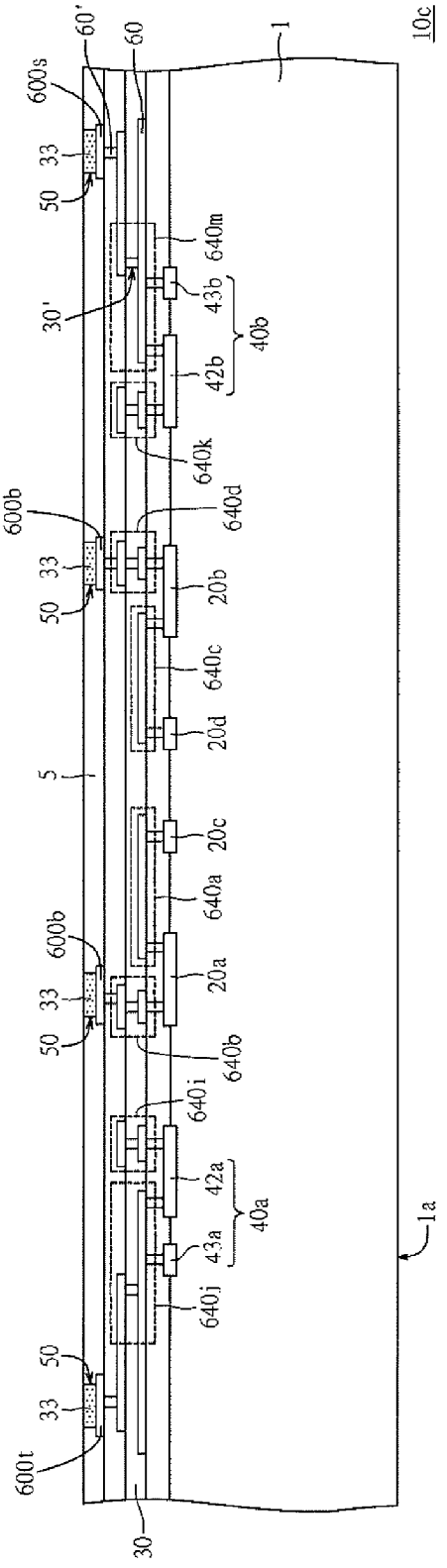


Fig. 46B

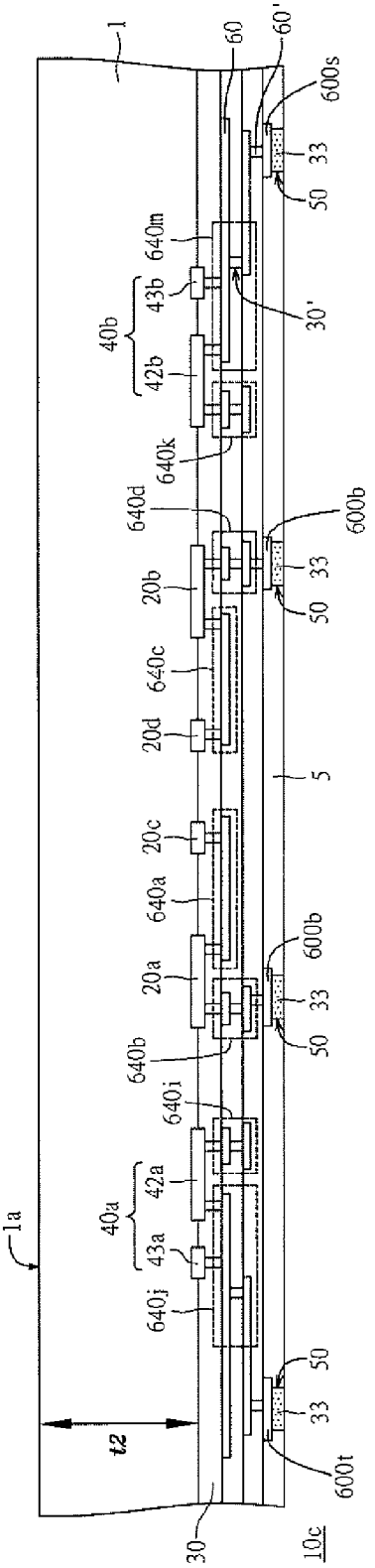


Fig. 46C

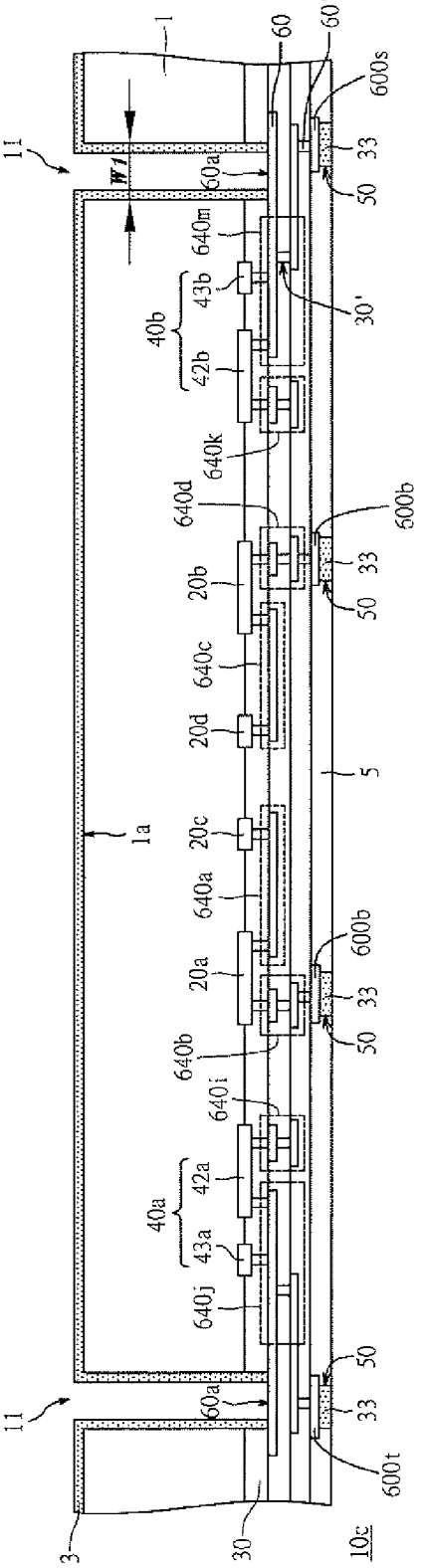


Fig. 46D

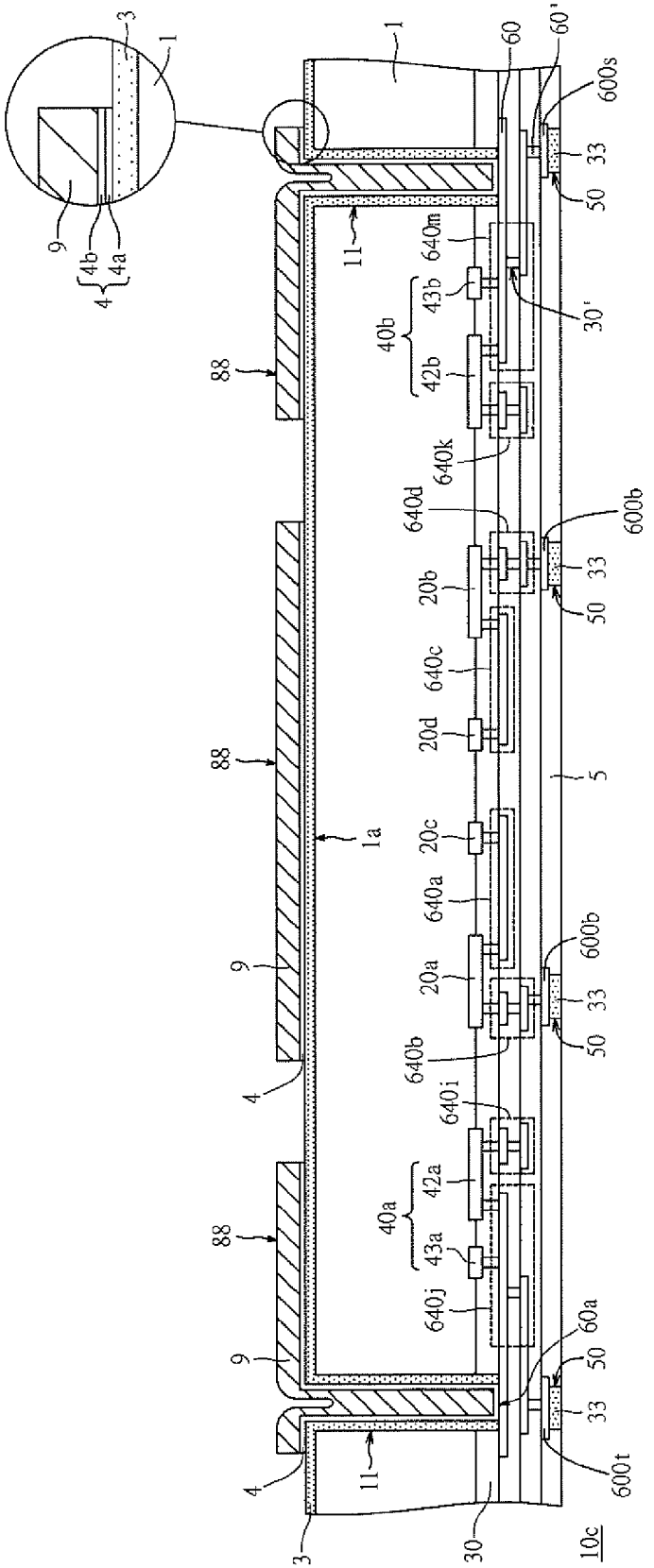

3
1
9
4b
4a
4
1
60
60'
600s
33
50
11
640m
43b
40b
42b
30'
88
640k
640d
600b
20b
640c
20d
5
1a
20c
640a
9
20a
640b
640i
42a
40a
43a
640j
60a
600t
30
10c

Fig. 46E

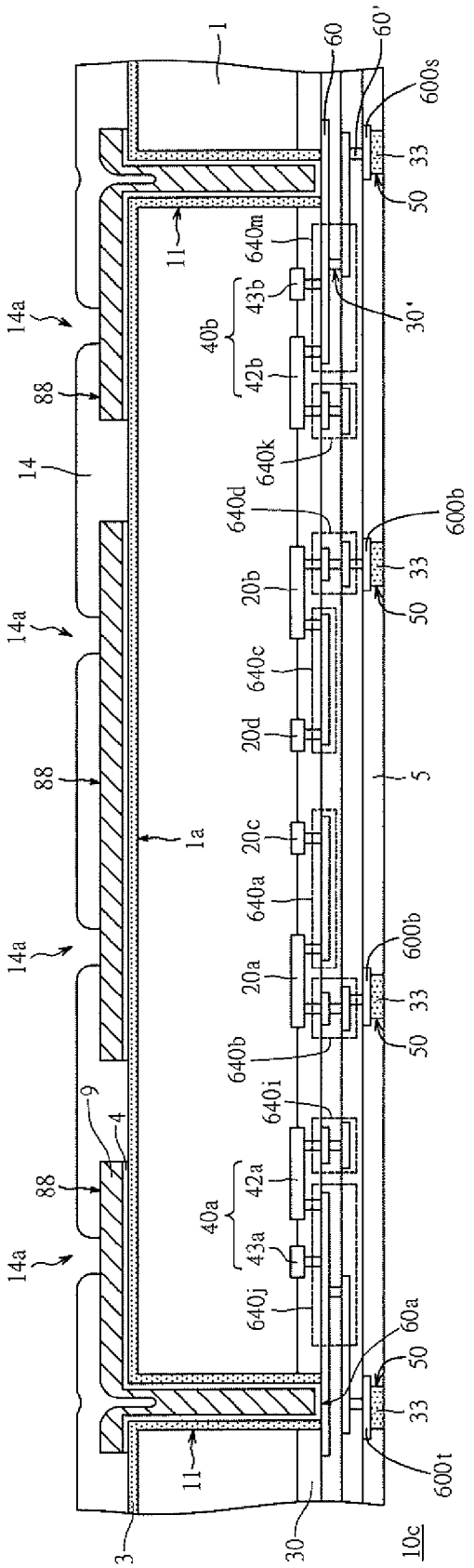

1
60
60'
600s
33
50
11
640m
43b
40b
42b
30'
14a
88
14
640k
640d
600b
20b
640c
20d
5
1a
20c
640a
20a
640b
640i
9
4
42a
40a
43a
640j
60a
600t
3
30
10c

Fig. 46F

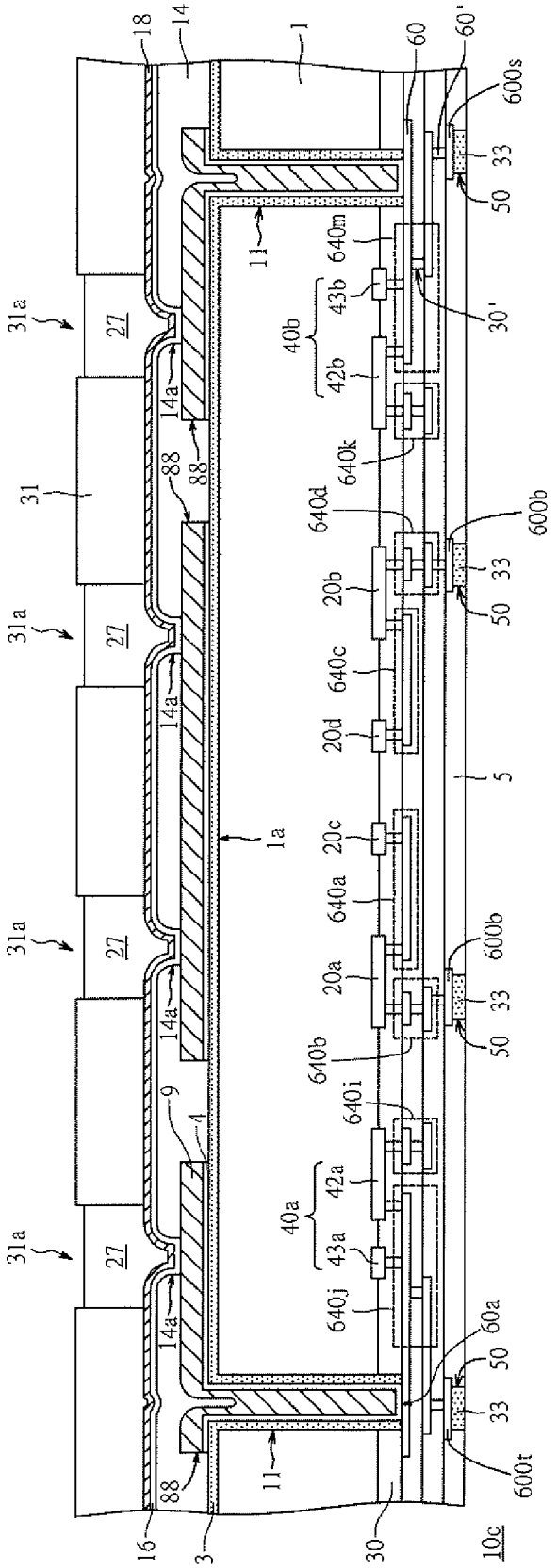

18
14
1
60
60'
600s
33
50
11
640m
43b
40b
42b
30'
31a
27
14a
88
640k
640d
600b
31
20b
640c
20d
5
1a
20c
640a
20a
640b
640i
9
4
42a
40a
43a
640j
60a
600t
16
3
30
10c

Fig. 46G

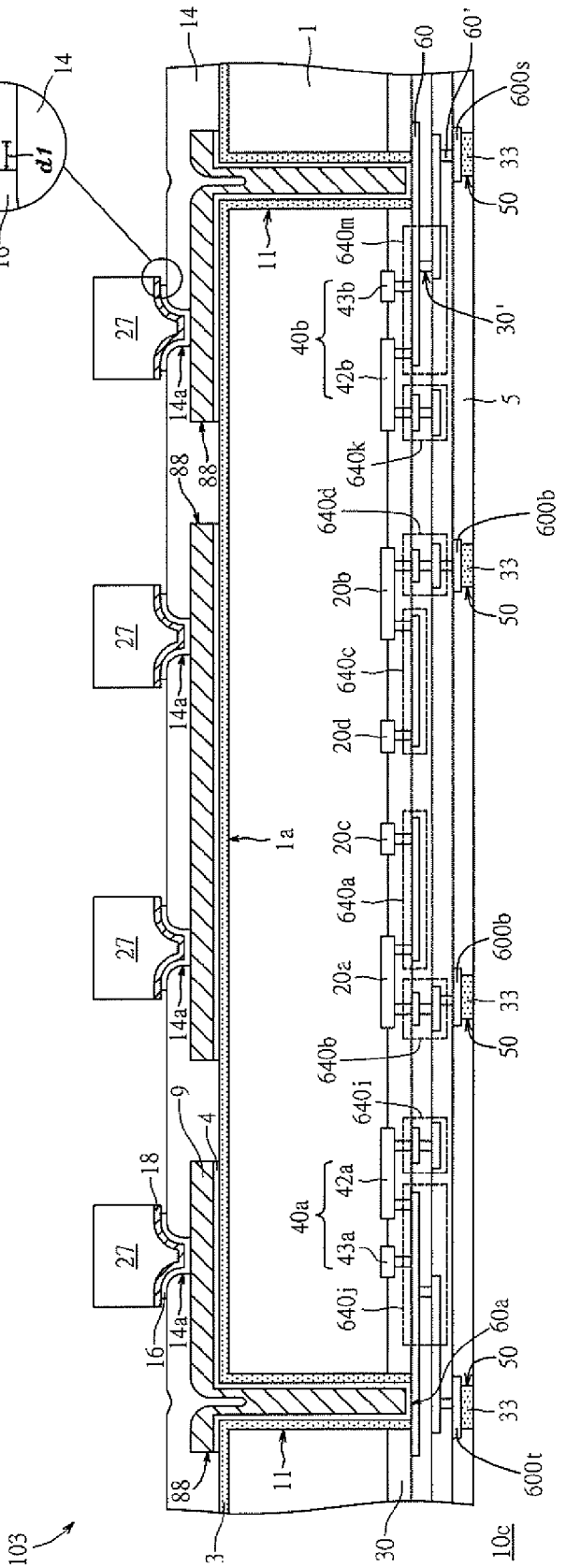

14
1
60
60'
600s
33
50
640m
43b
40b
42b
30'
5
640k
640d
600b
20b
640c
20d
1a
20c
640a
20a
640b
640i
42a
40a
43a
640j
60a
600t
10c
30
3
11
88
14a
16
18
27
d1
103
9
4

Fig. 46H

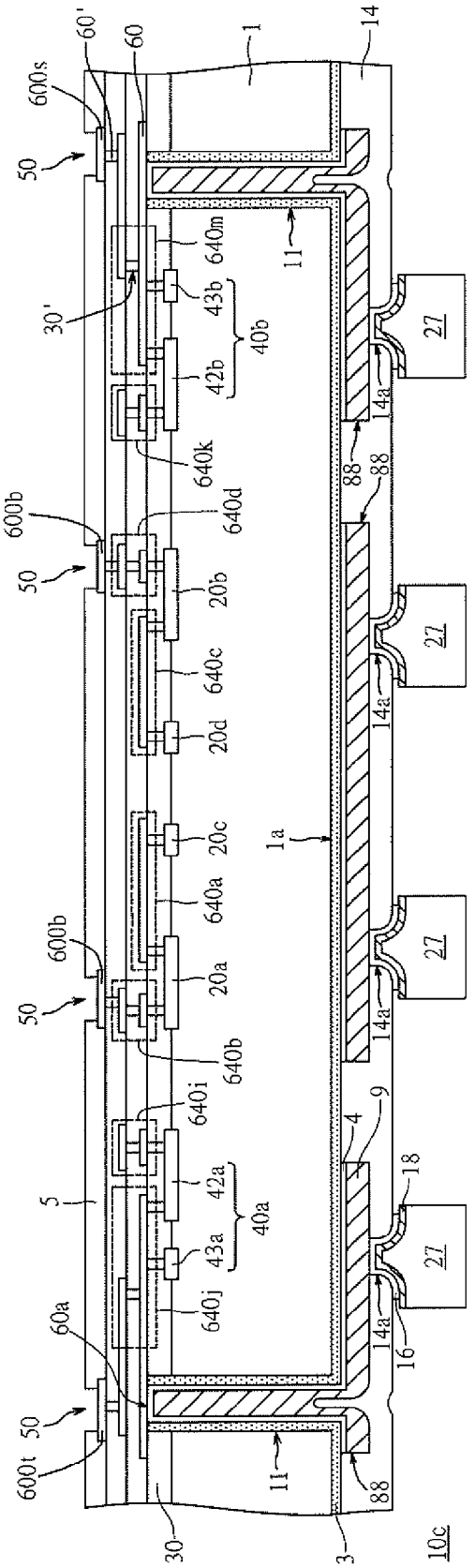

60'
60
600s
1
14
50
640m
43b
40b
11
30'
27
42b
14a
640k
88
88
600b
640d
50
20b
640c
20d
20c
1a
640a
600b
20a
50
640b
640i
9
4
18
5
42a
40a
43a
27
640j
60a
14a
16
50
600t
11
88
30
3
10c

Fig. 46I

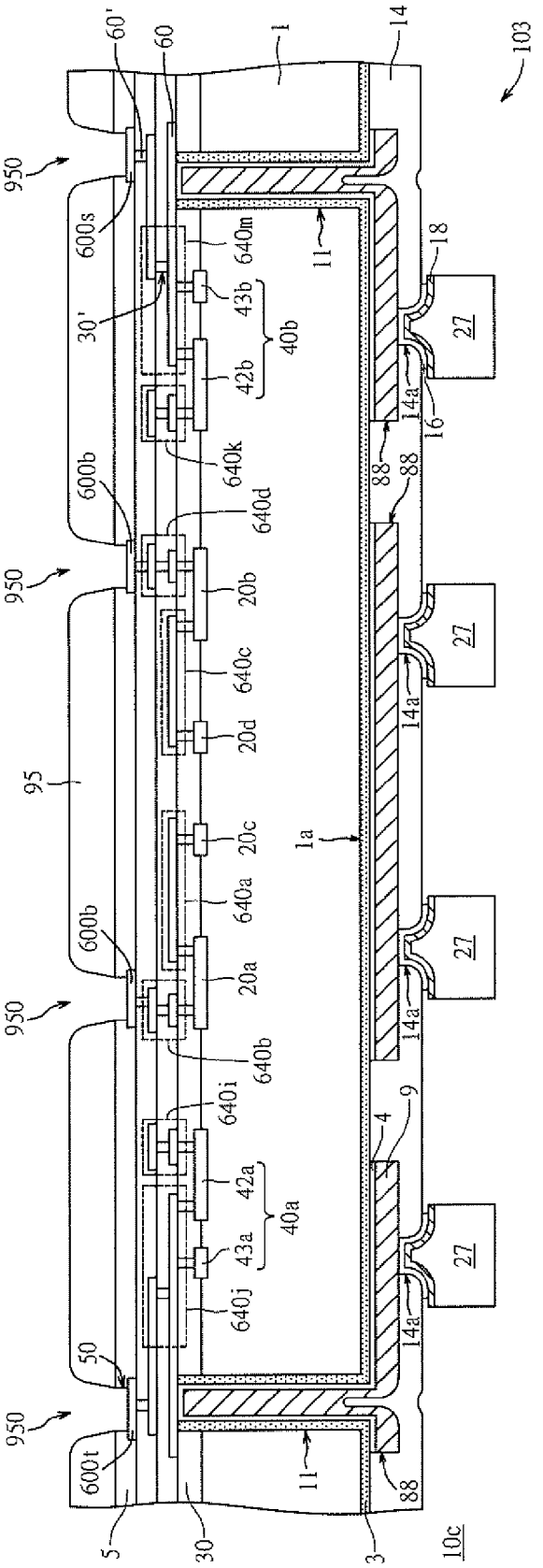

60'
60
1
14
103
950
600s
640m
43b
40b
42b
30'
11
18
27
14a
16
88
640k
640d
600b
20b
640c
20d
95
20c
1a
640a
20a
640b
640i
42a
40a
43a
640j
9
4
50
600t
5
30
3
10c

Fig. 46J

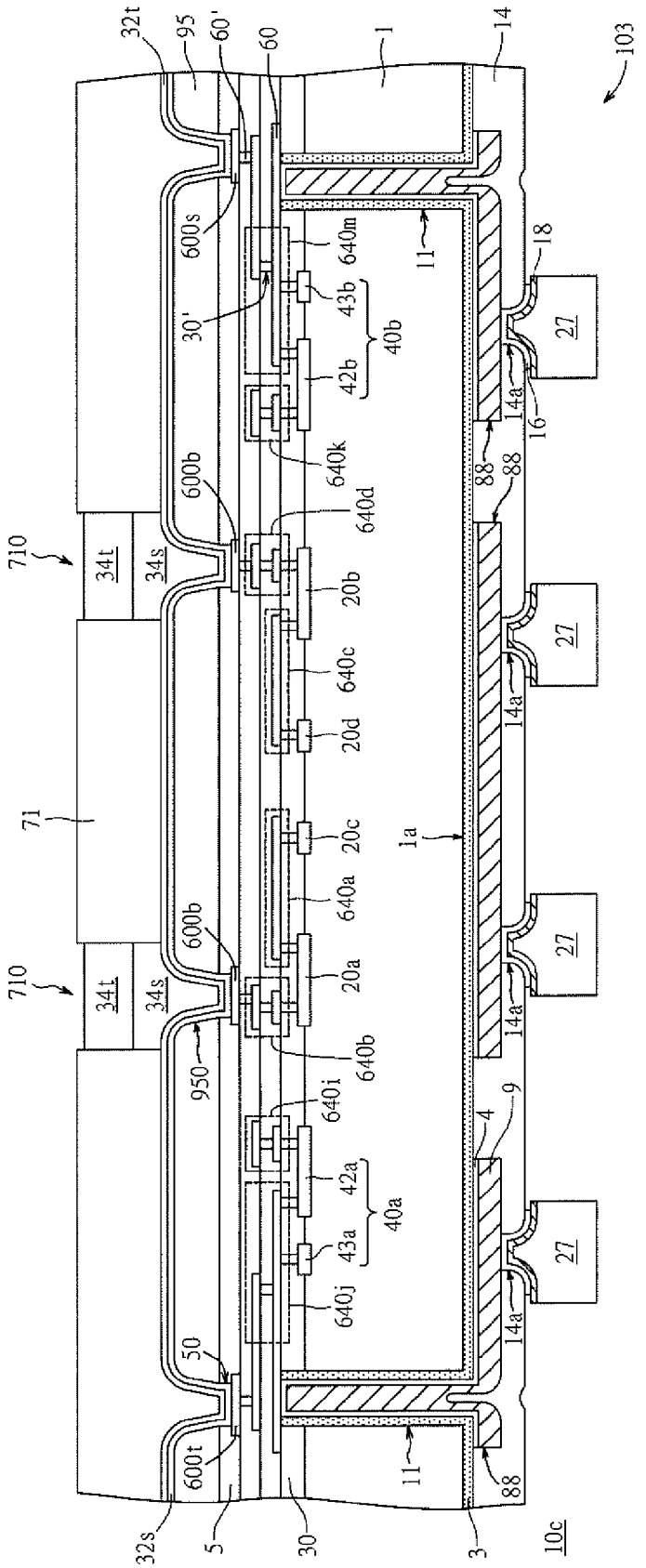

32t
95
60'
60
1
14
103
600s
640m
11
18
30'
43b
40b
42b
27
14a
16
640k
88
600b
640d
710
34t
34s
20b
640c
20d
71
20c
1a
640a
20a
640b
950
640i
9
4
42a
40a
43a
640j
50
600t
32s
5
30
3
10c

Fig. 46K

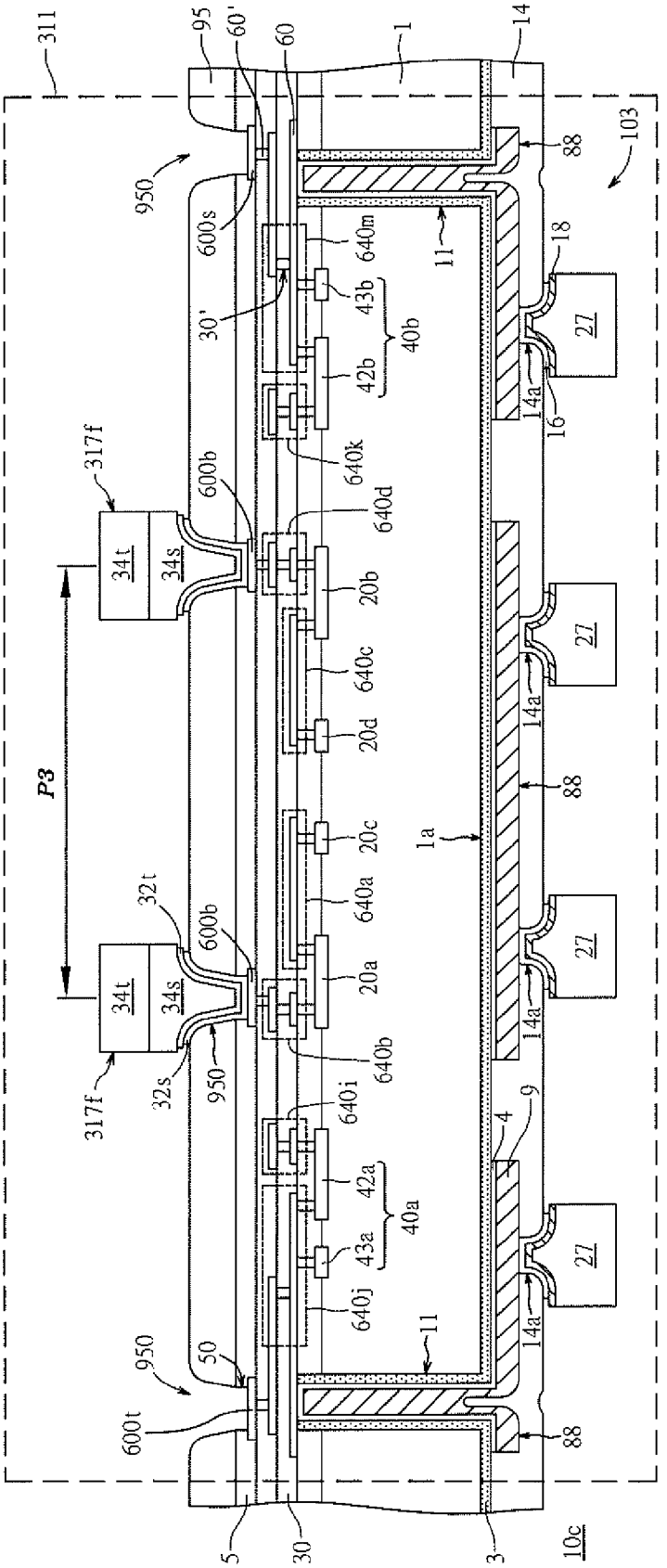

311
95
60'
60
1
14
103
88
950
600s
640m
43b
40b
42b
30'
11
18
27
14a
16
317f
600b
640k
640d
34t
34s
20b
640c
20d
20c
1a
20a
640a
32t
640b
32s
640i
42a
40a
43a
640j
9
4
50
600t
5
30
3
10c
P3

Fig. 46L

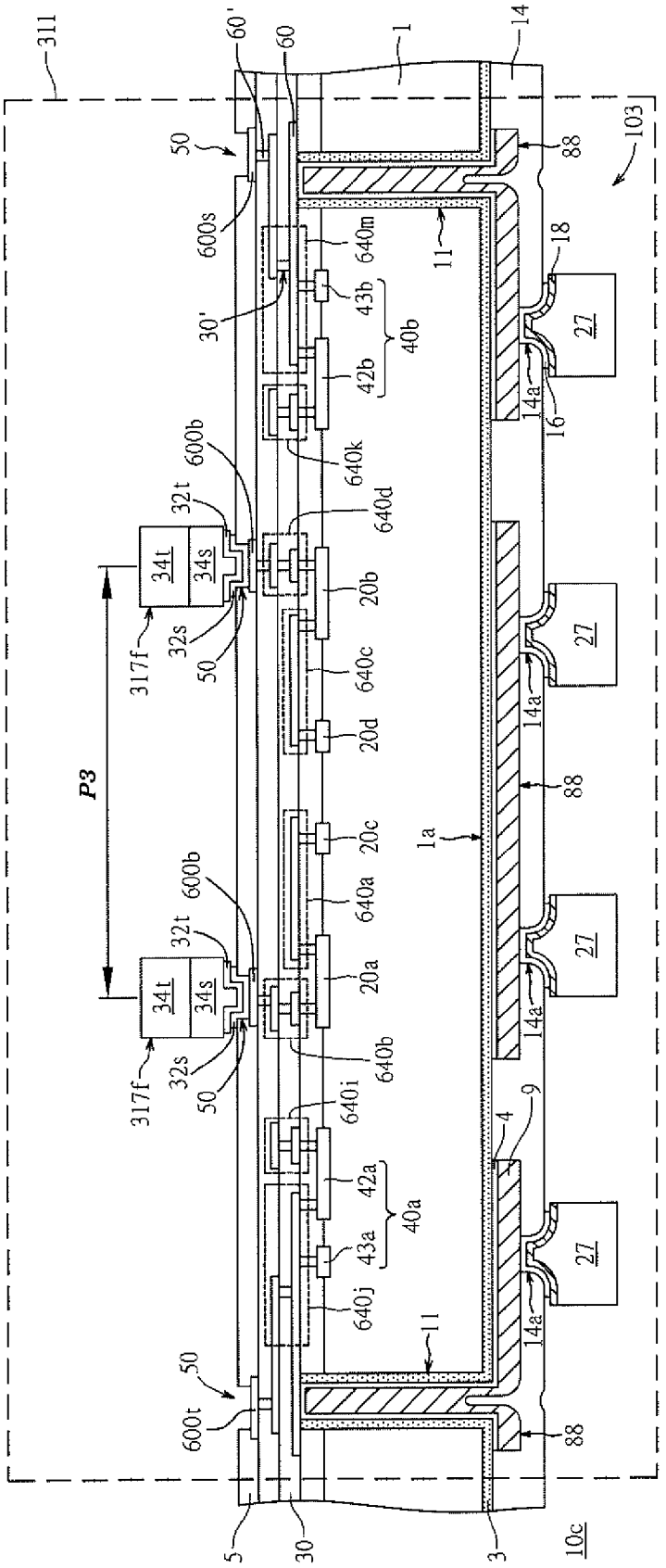

311
60'
60
1
14
103
50
600s
88
640m
11
18
43b
40b
30'
42b
27
14a
16
600b
640k
32t
640d
34t
34s
20b
317f
32s
50
640c
20d
P3
20c
1a
640a
20a
640b
640i
9
4
42a
40a
43a
640j
600t
5
30
3
10c

Fig. 46M

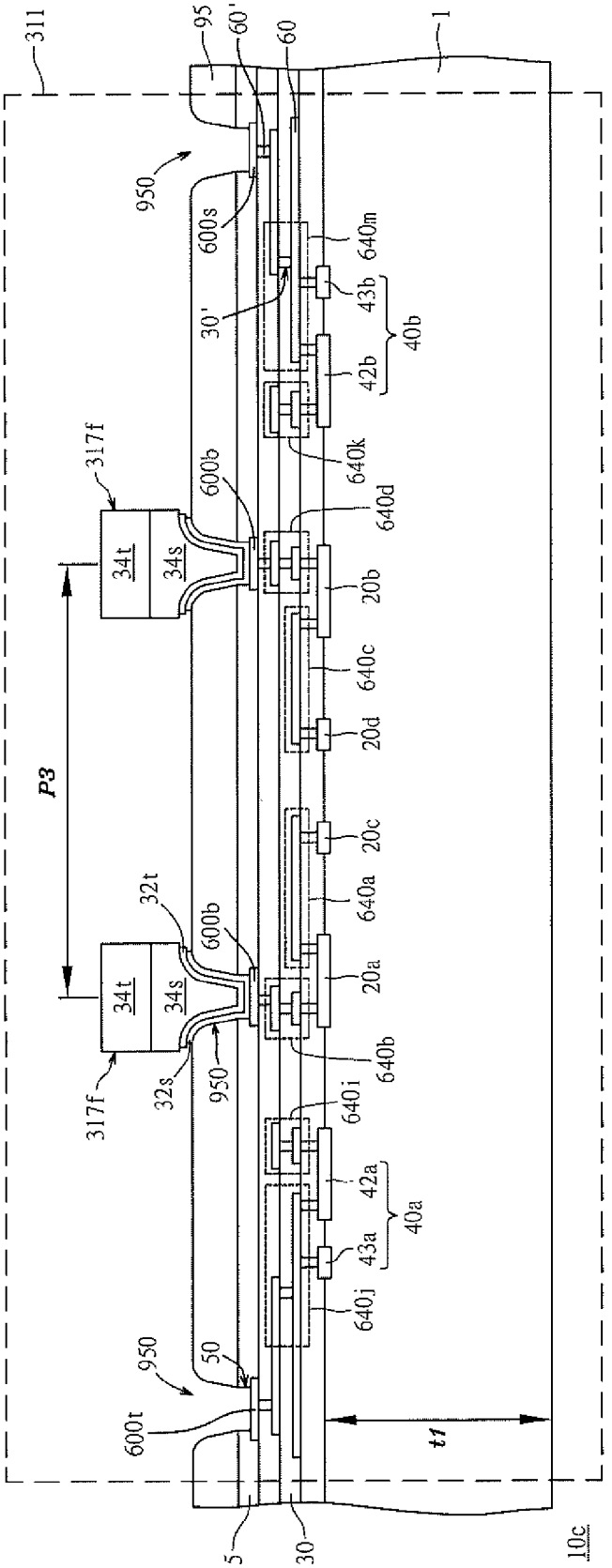

311
95
60'
60
1
950
600s
640m
43b
40b
42b
30'
317f
640k
600b
640d
34t
34s
20b
640c
20d
P3
20c
32t
640a
20a
640b
640i
42a
40a
43a
640j
32s
950
317f
950
50
600t
t1
5
30
10c

Fig. 46N

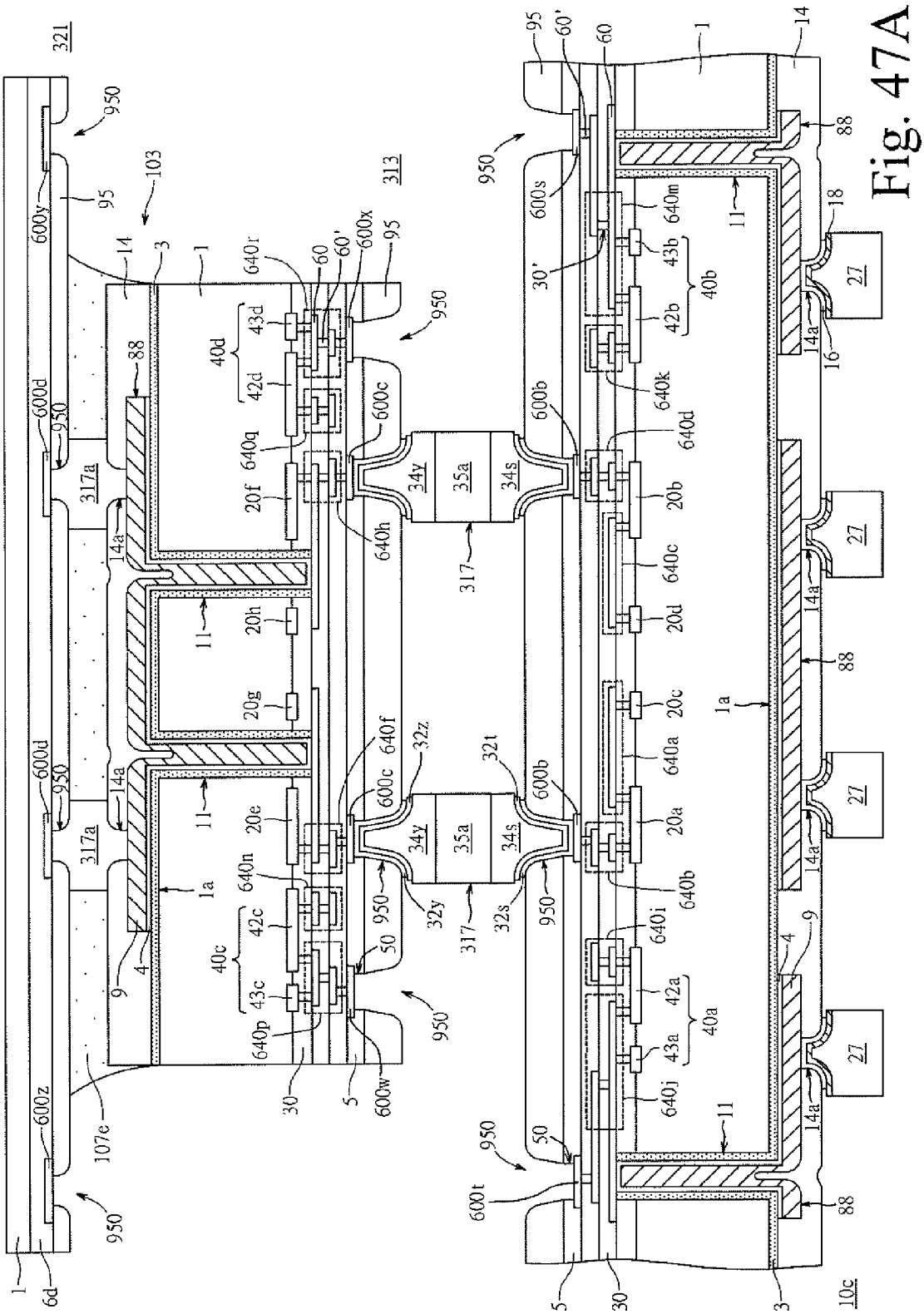


Fig. 47A

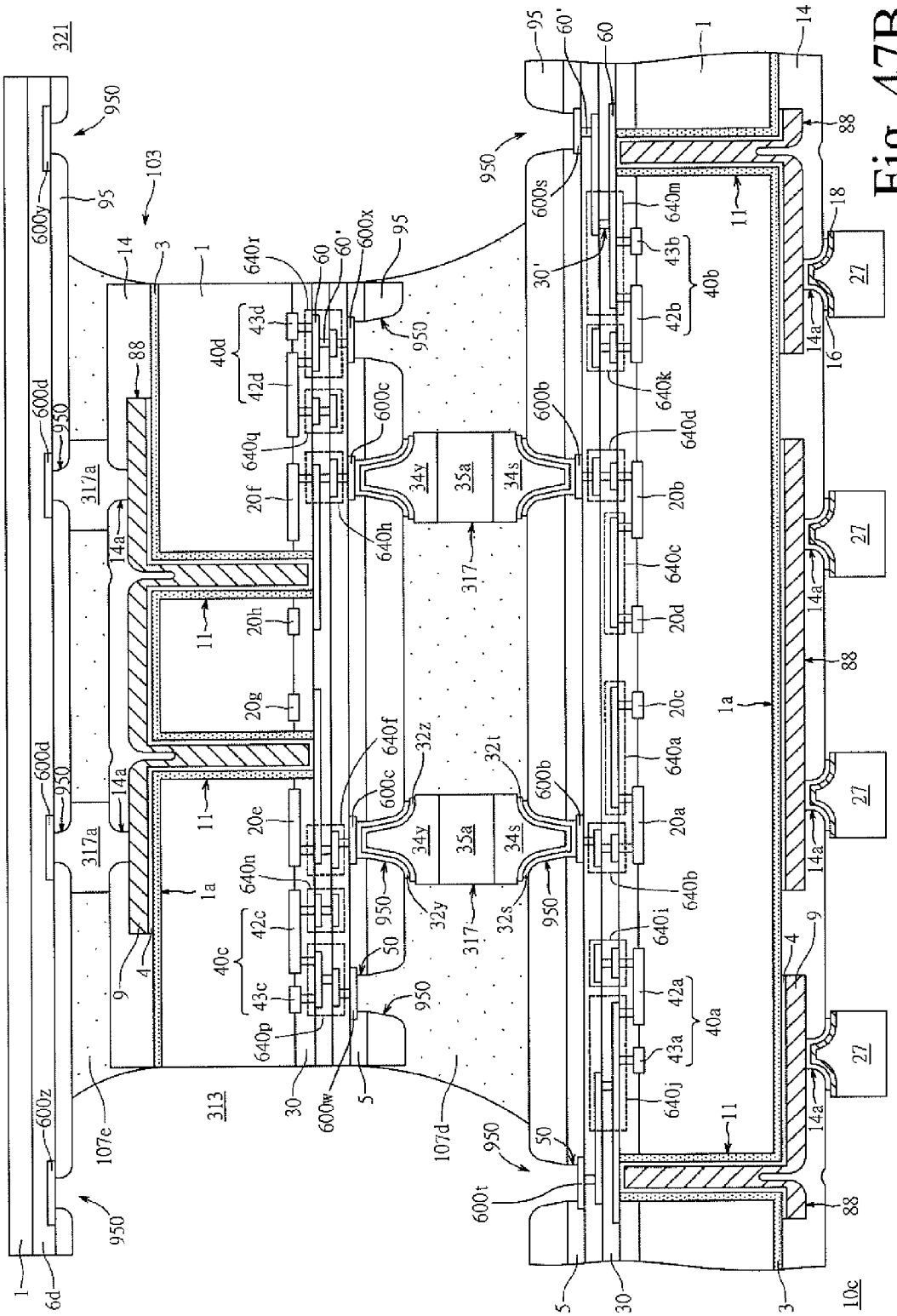


Fig. 47B

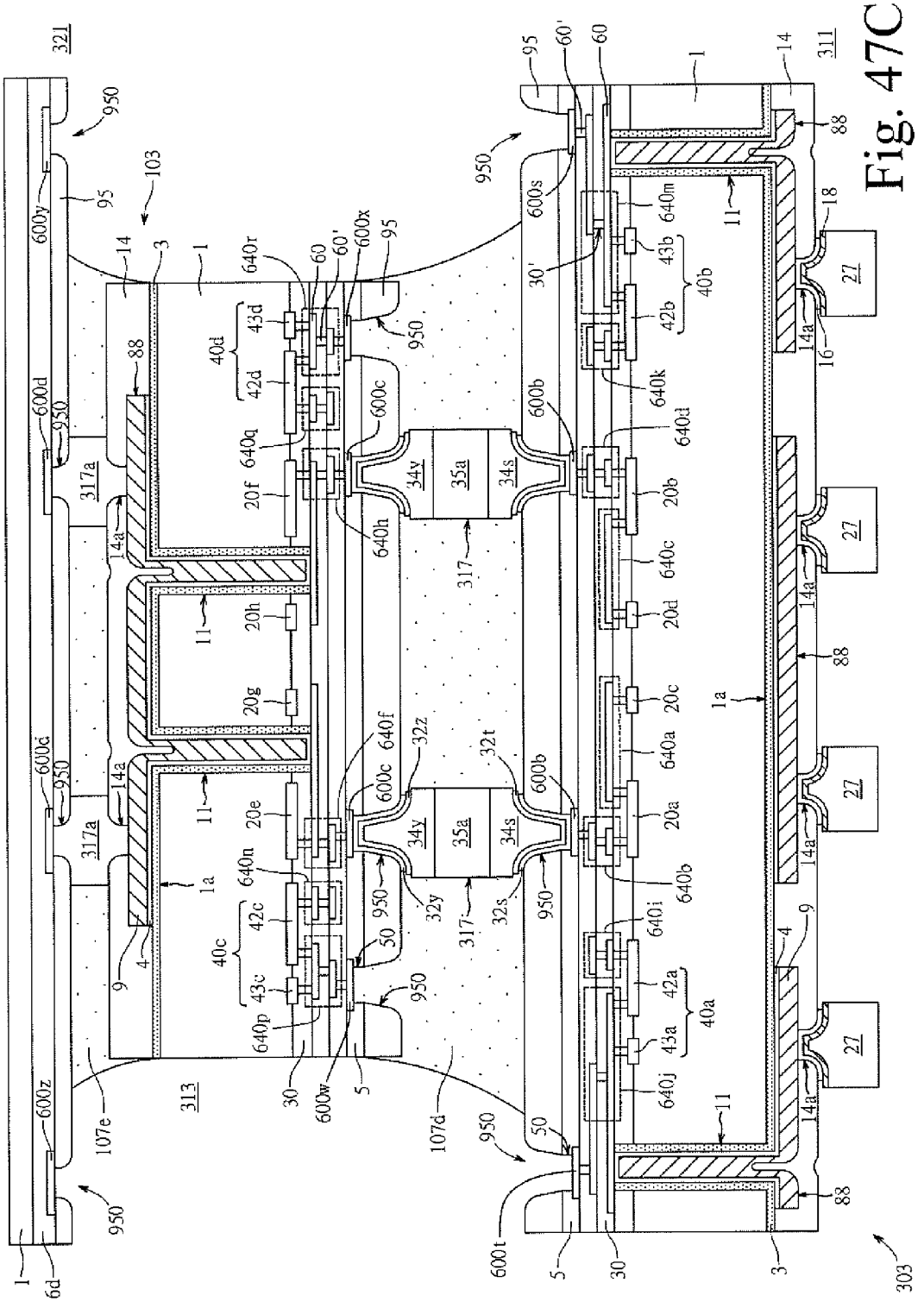


Fig. 47C

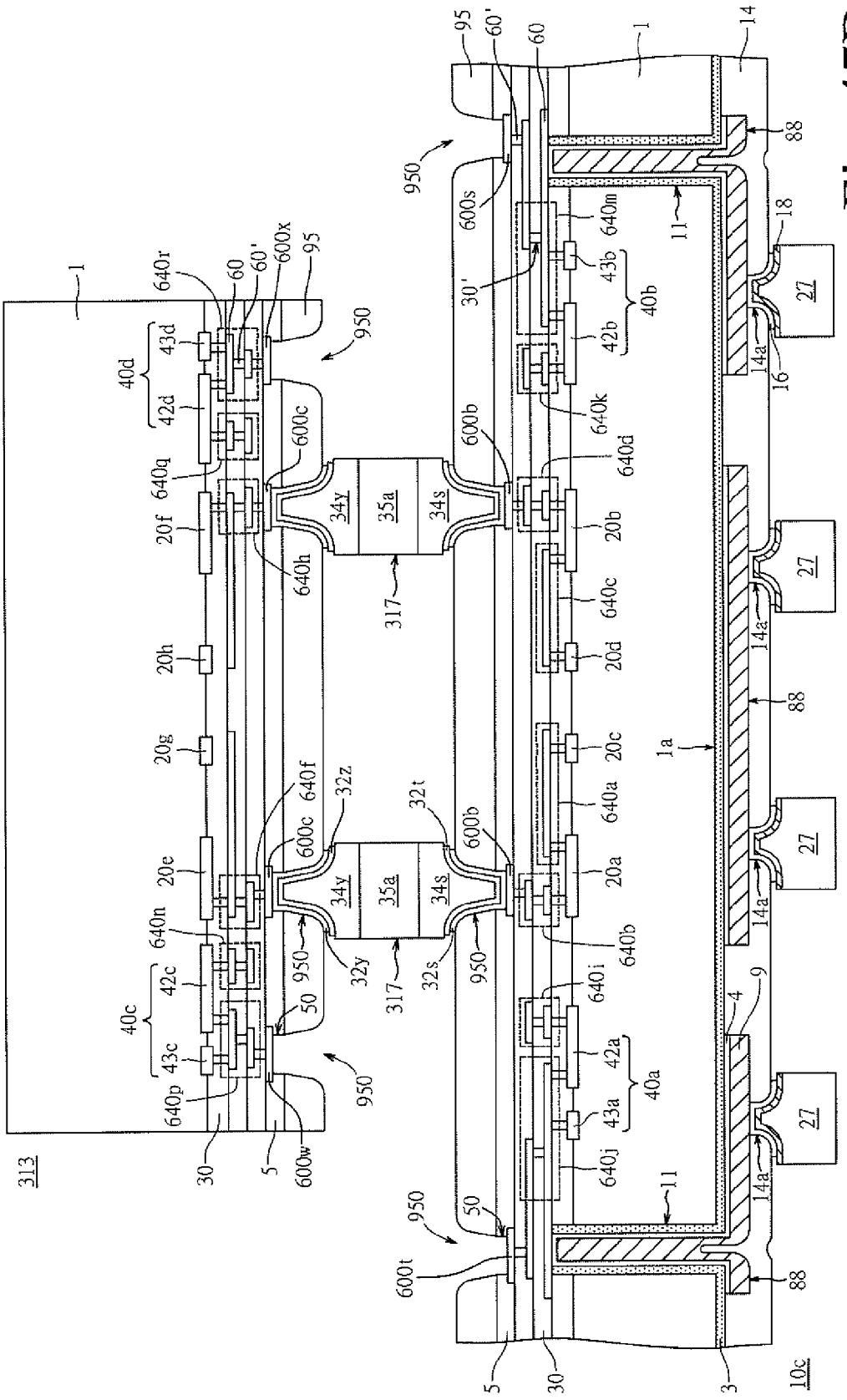


Fig. 47D

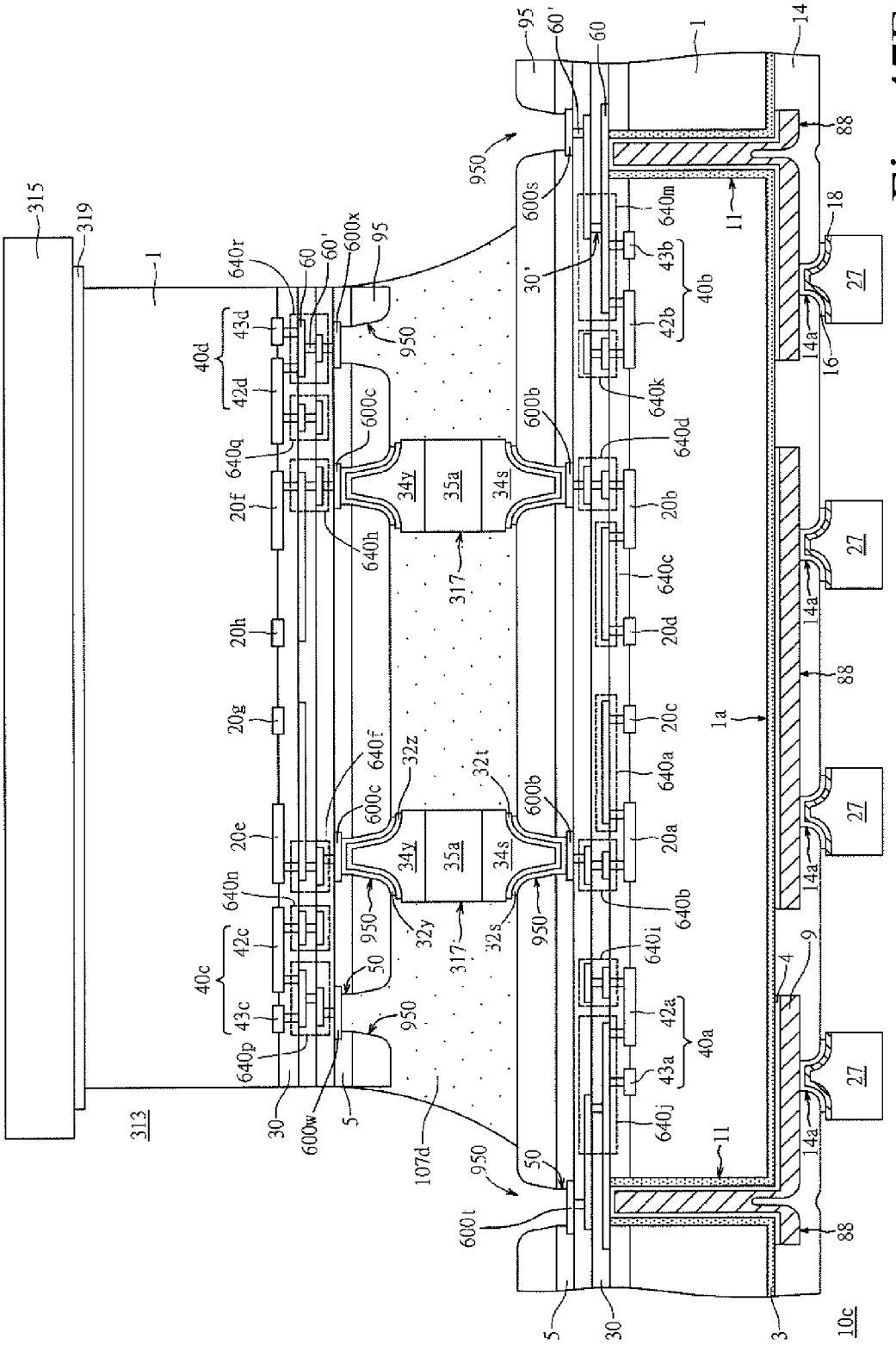

315
319
313
1
640r
60
60'
600x
95
950
40d
43d
42d
640q
20f
600c
34y
35a
34s
640h
317
20h
20g
20e
640n
40c
42c
43c
640p
640f
32z
32t
32y
32s
50
30
600w
5
107d
600l
600b
600s
30'
640m
43b
42b
40b
640k
640d
20b
640c
20d
20c
640a
20a
640b
640i
42a
40a
43a
640j
11
18
27
14a
16
88
14
1a
4
9
3
10c

Fig. 47E

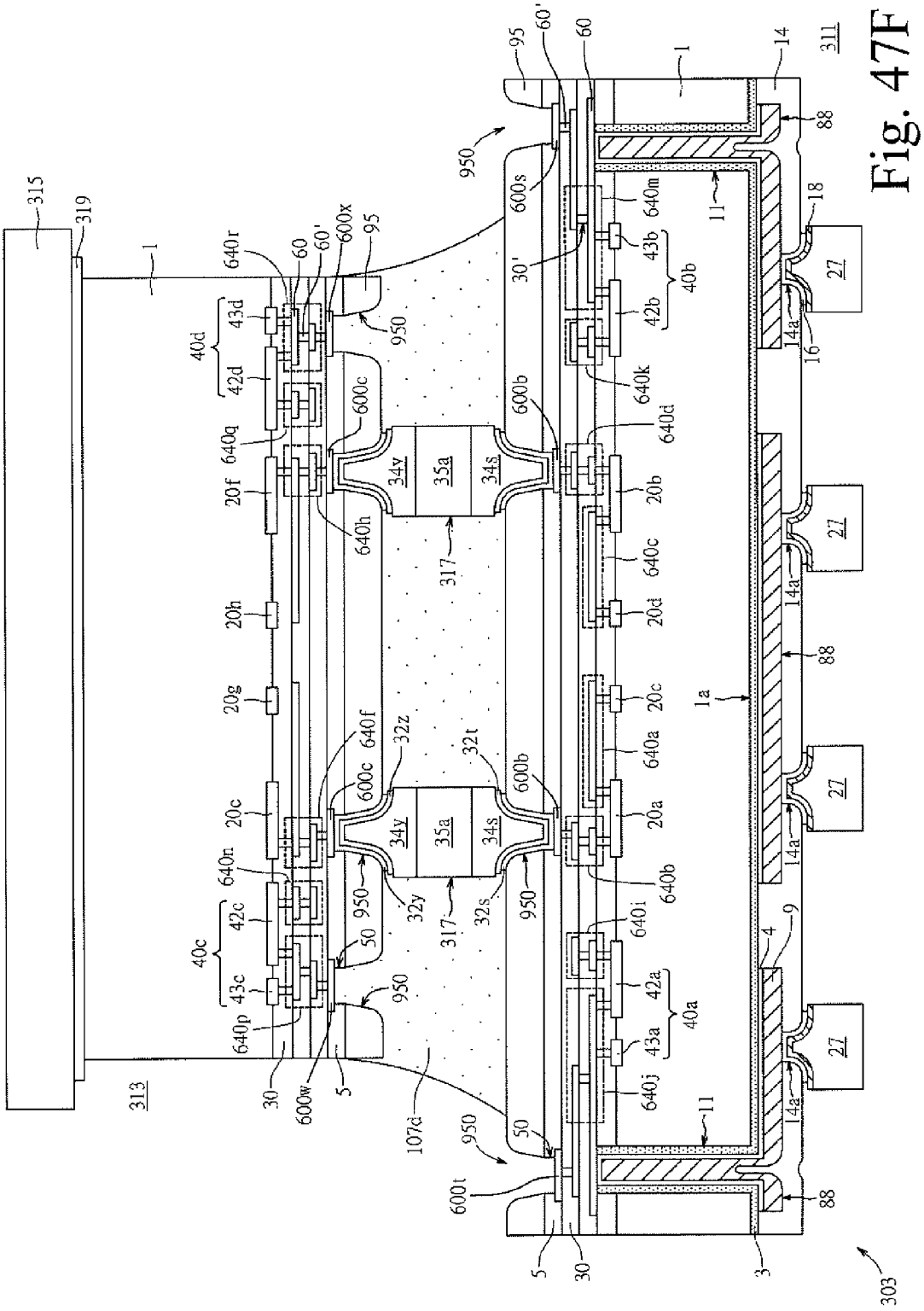

315
319
313
1
640r
60
60'
600x
95
950
40d
43d
42d
640q
20f
600c
640h
34y
35a
34s
317
20h
20g
640f
32z
32t
20c
640n
42c
40c
43c
640p
30
600w
5
50
32y
32s
107a
600t
30'
600s
640m
43b
40b
42b
640k
600b
640d
20b
640c
20d
20c
1a
640a
20a
640b
640i
42a
40a
43a
640j
11
88
18
27
14a
16
14
311
9
4
3
303

Fig. 47F

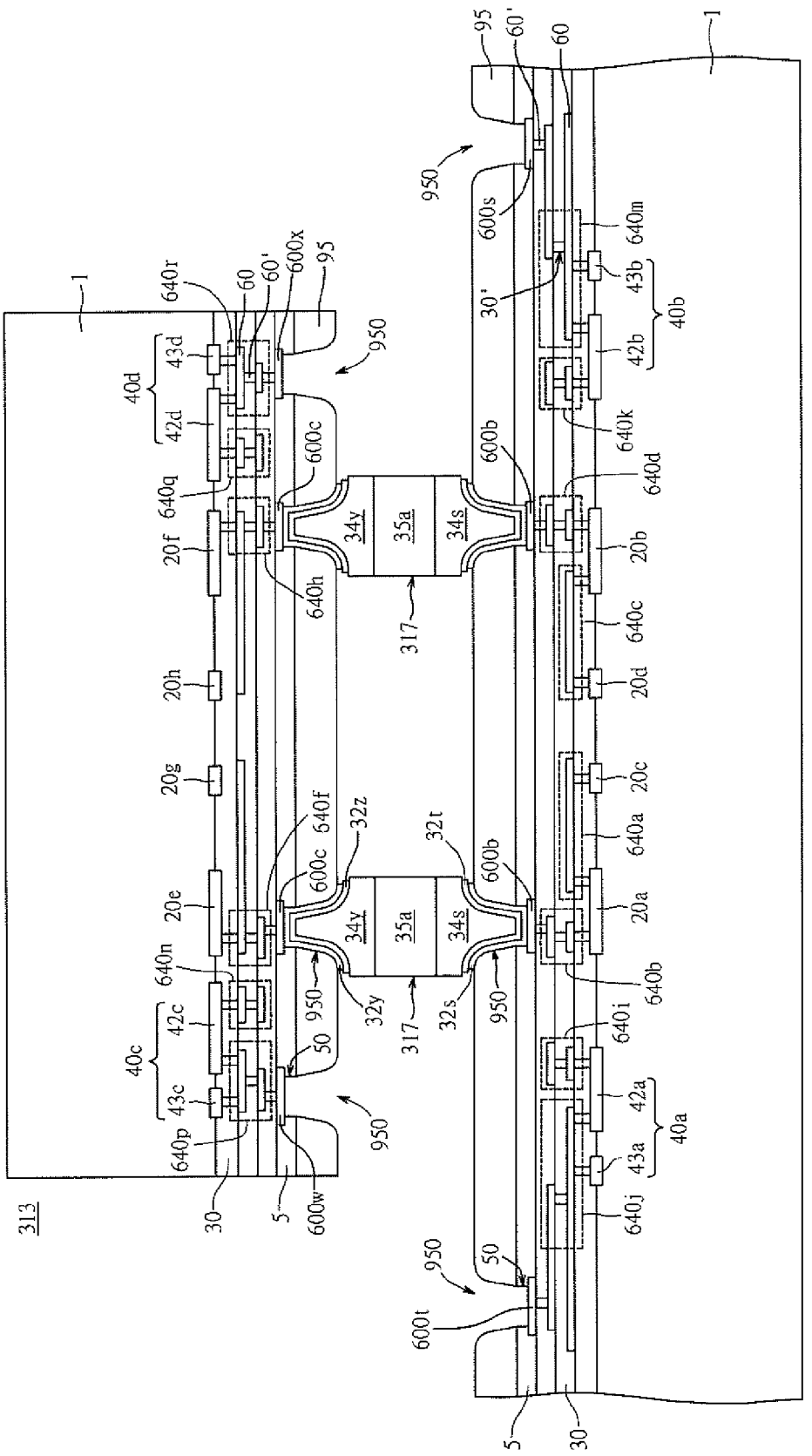

1
95
60'
60
950
600s
30'
640m
43b
40b
42b
640k
600b
640d
20b
640c
20d
20c
640a
20a
640b
640i
42a
40a
43a
640j
50
600t
5
30
10c
313
600w
600x
640r
60
60'
40d
43d
42d
600c
640q
20f
640h
317
34y
35a
34s
20h
20g
640f
32z
32t
20e
640n
40c
42c
43c
640p
32y
32s
950
50

Fig. 47G

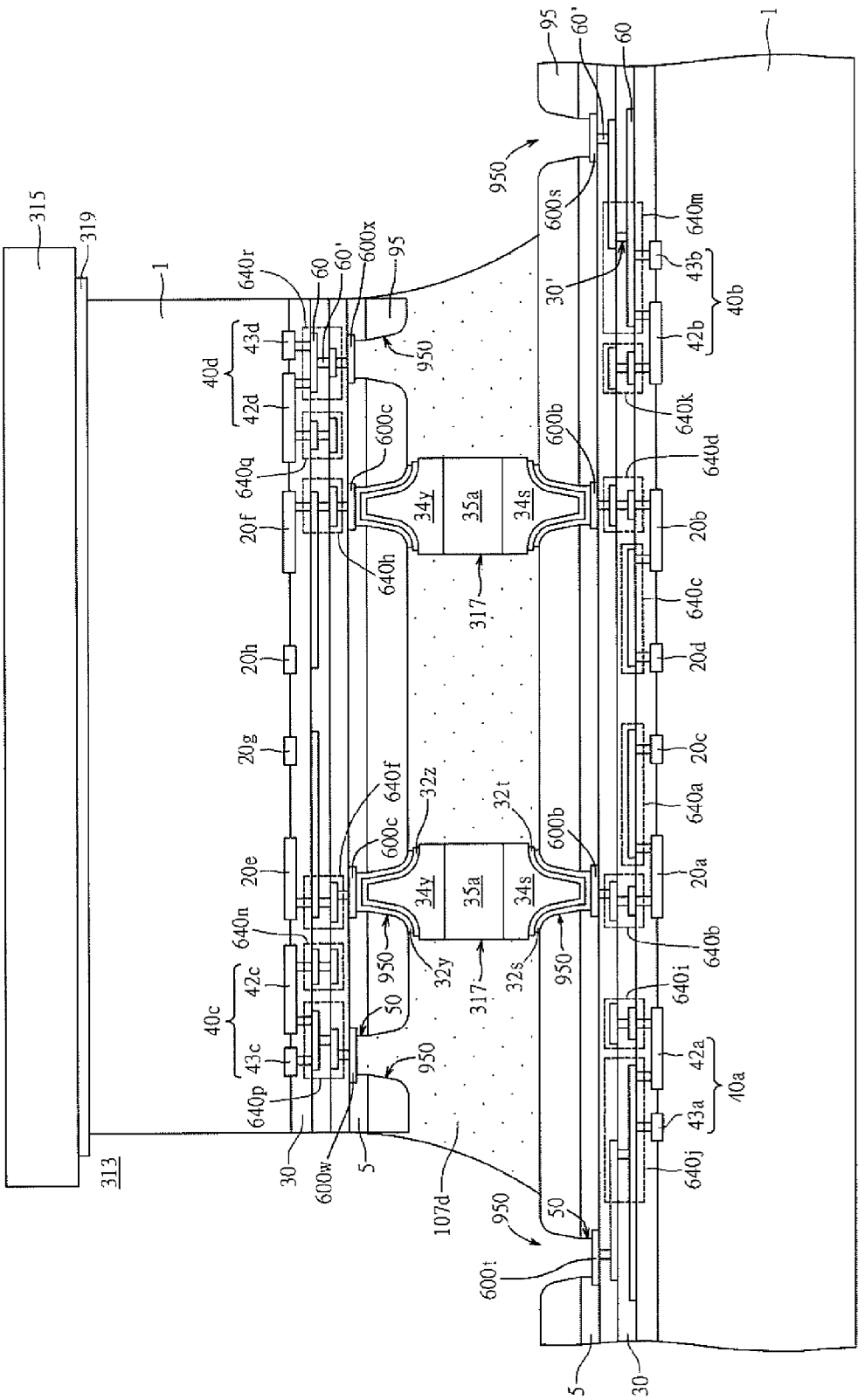

315
319
313
1
640r
60
60'
600x
95
950
600s
30'
640m
43b
40b
42b
40d
43d
42d
600c
640q
20f
640h
34y
35a
34s
317
600b
640k
640d
20b
640c
20d
20h
20g
640f
32z
32t
20e
640n
42c
40c
43c
640p
50
32y
32s
640i
640b
20a
640a
20c
42a
43a
40a
640j
30
600w
5
107d
600t
10c

Fig. 47H

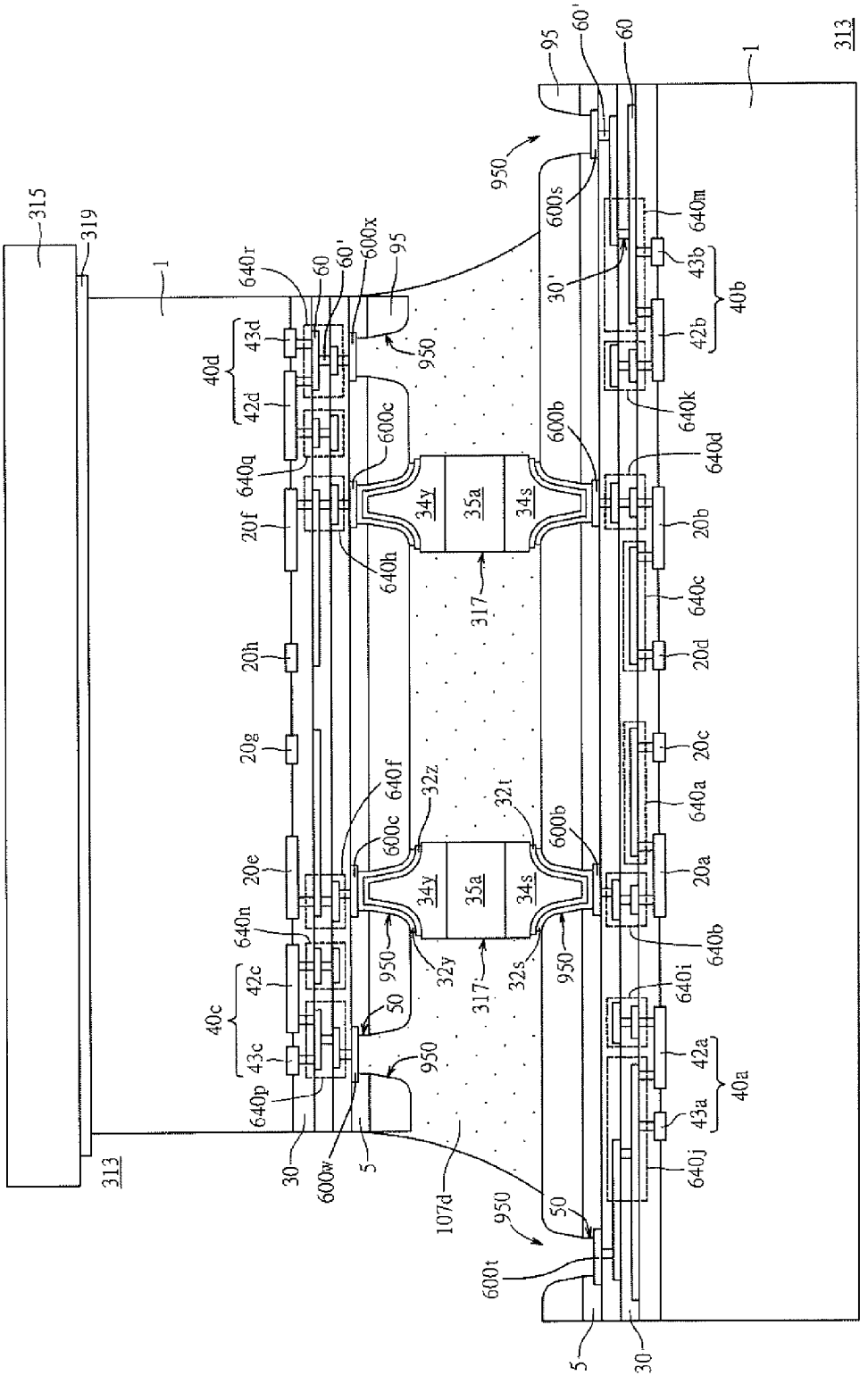

315
319
313
1
640r
60
60'
600x
95
950
600s
30'
640m
43b
42b
40b
640k
640d
20b
640c
20d
20c
640a
20a
640b
640i
42a
43a
40a
640j
303
40d
43d
42d
600c
640q
20f
640h
317
34y
35a
34s
600b
20h
20g
640f
32z
32t
20e
640n
42c
43c
40c
640p
50
32y
32s
30
600w
5
107d
600t

Fig. 47I

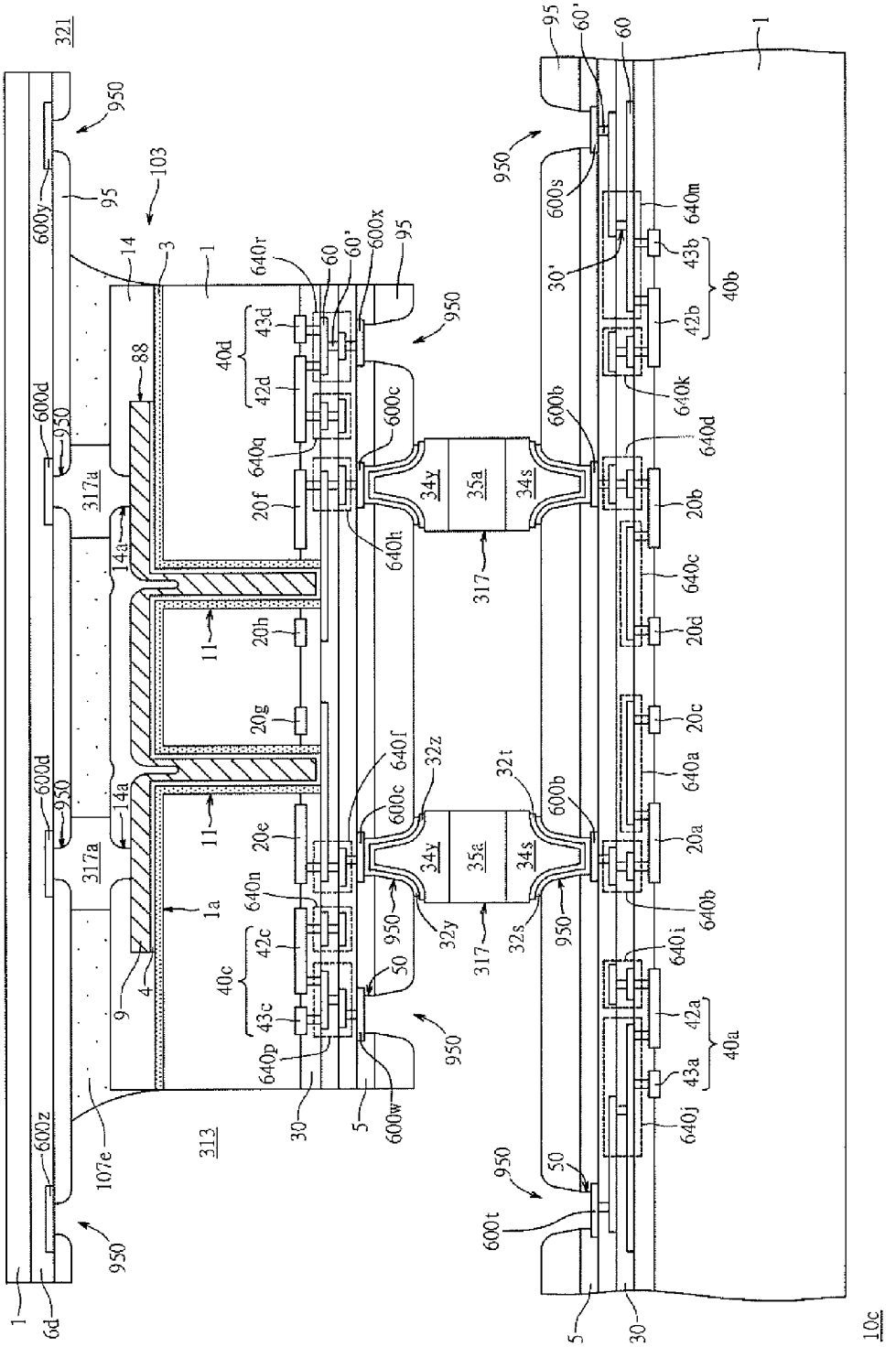

321
950
103
95
600y
14
3
1
640r
60
60'
600x
95
40d
43d
42d
88
600d
950
600c
640q
20f
317a
14a
640h
34y
35a
34s
317
11
20h
20g
600b
640d
20b
640c
20d
20c
640a
20a
640b
640i
42a
43a
40a
640j
640k
42b
43b
40b
640m
30'
600s
95
60'
60
1
950
600d
14a
317a
11
20e
640n
1a
600c
640f
32z
32t
600b
34y
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Fig. 47J

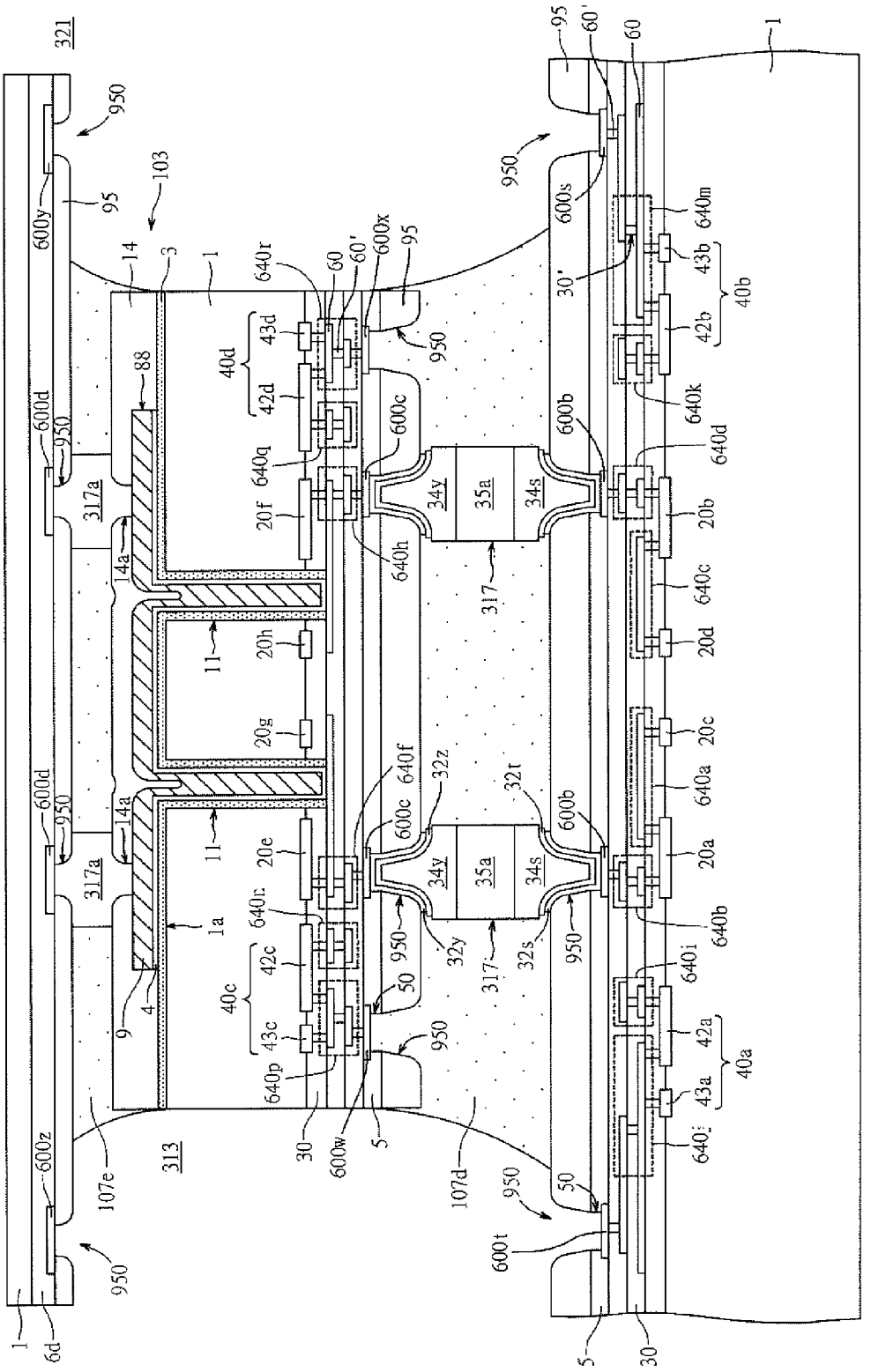


Fig. 47K

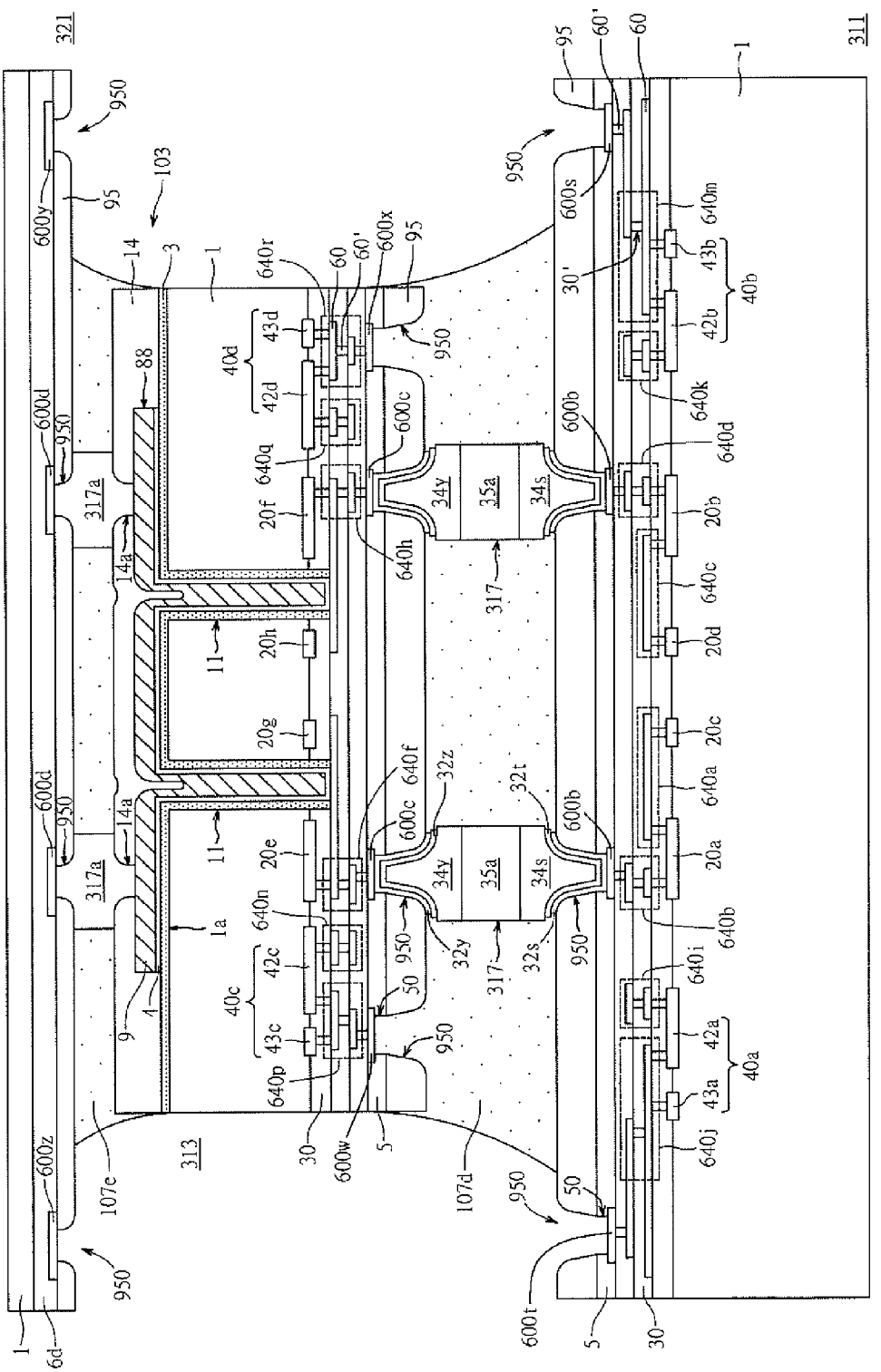


Fig. 47L

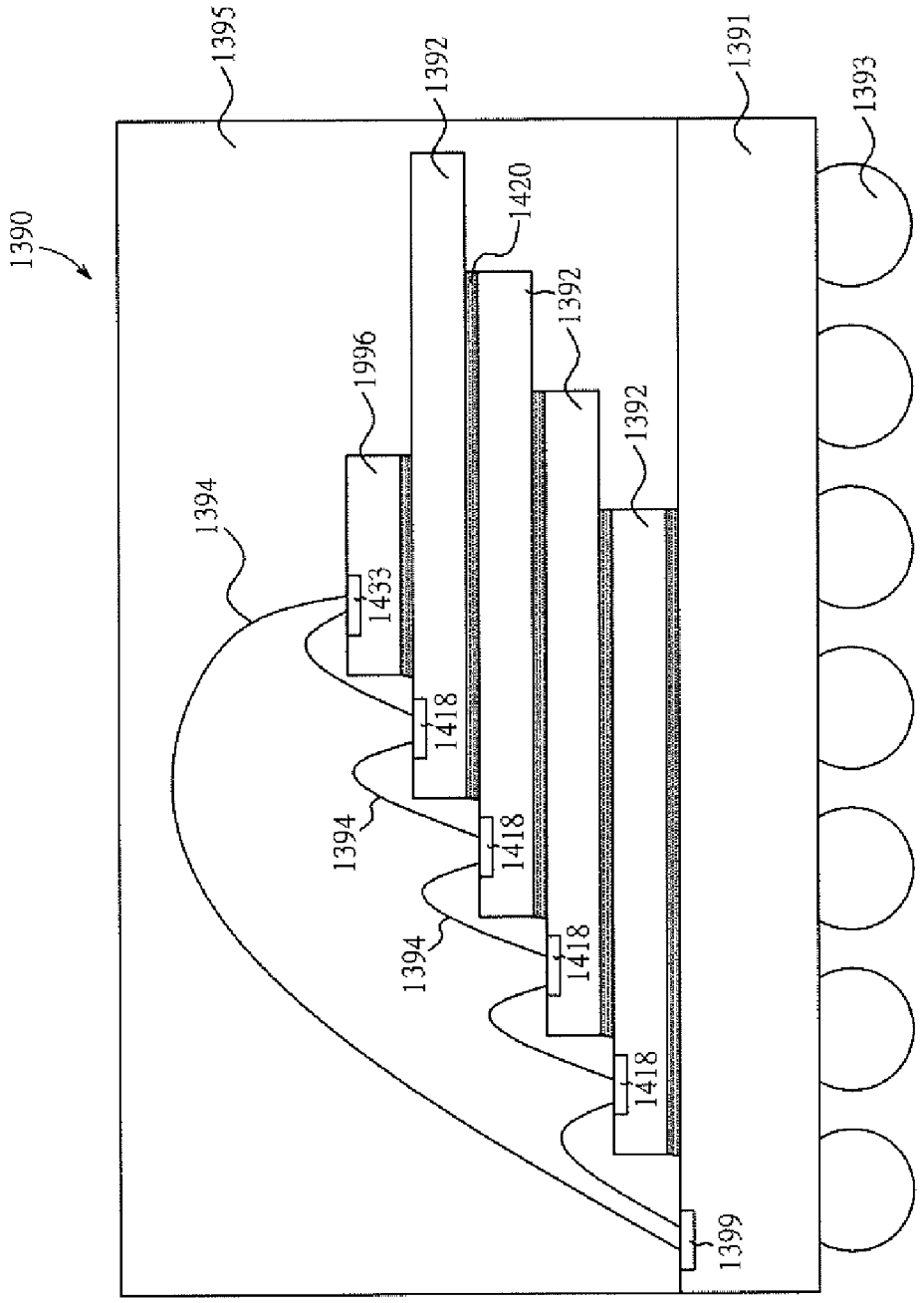

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Fig. 48A

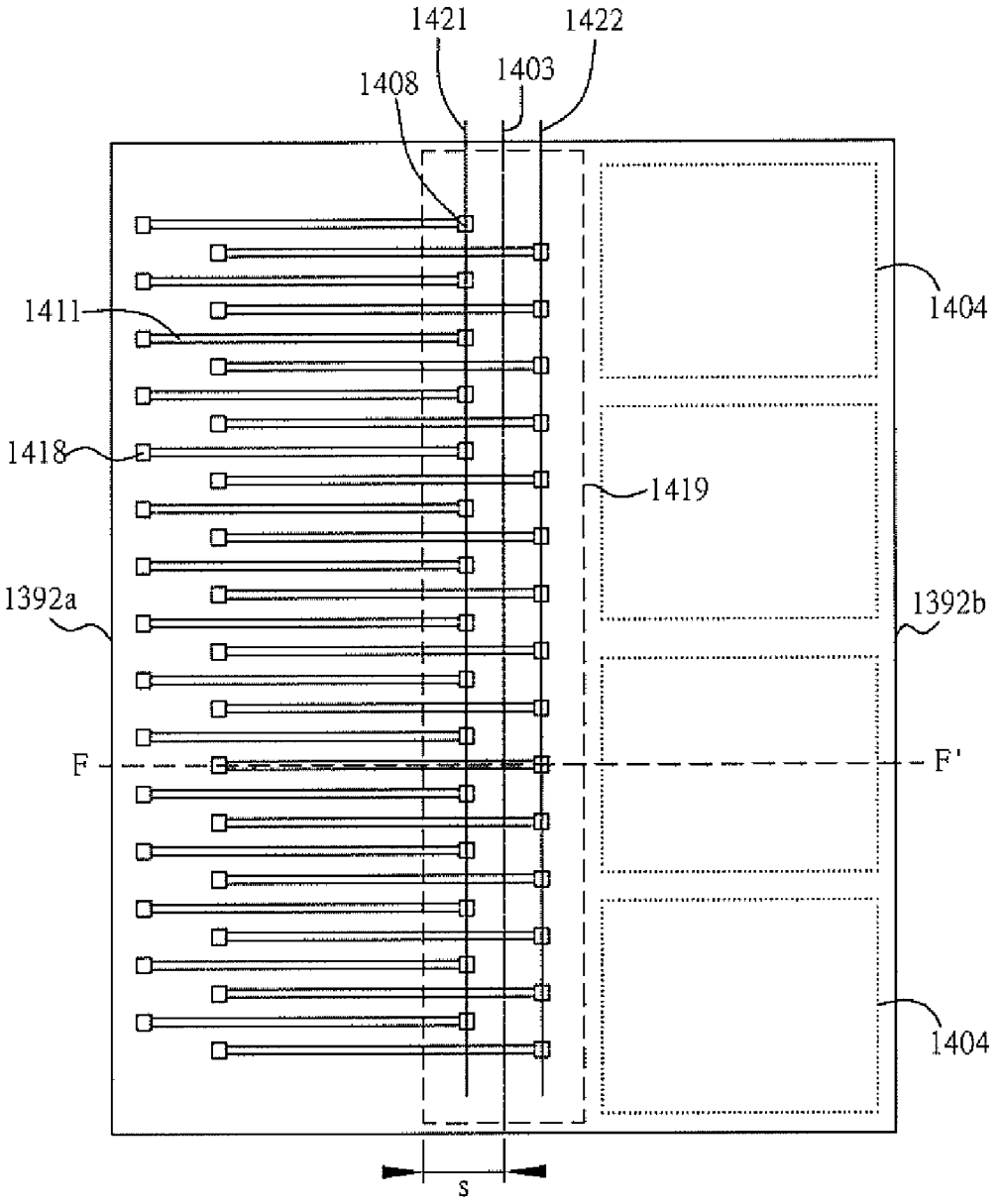


Fig. 48B

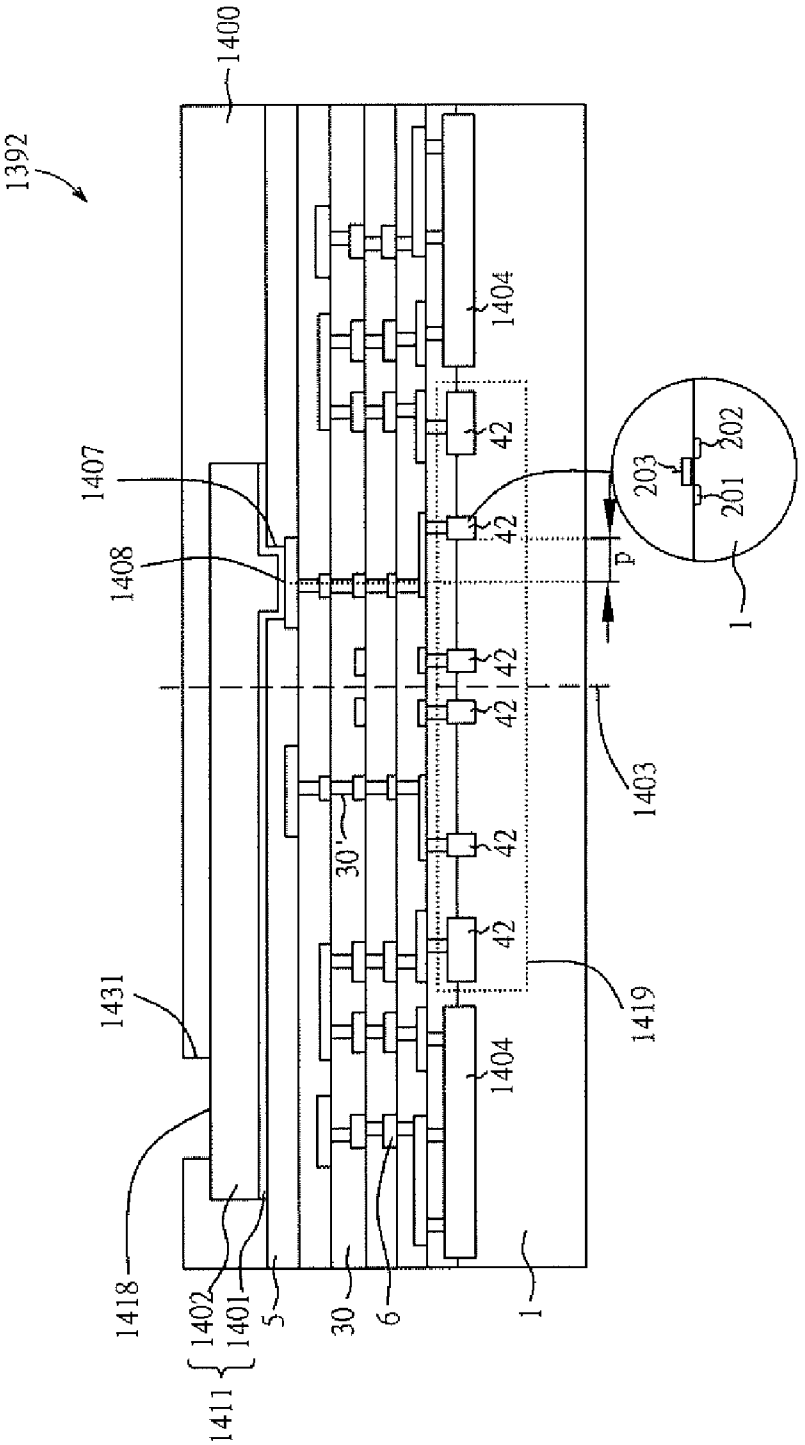

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Fig. 48C

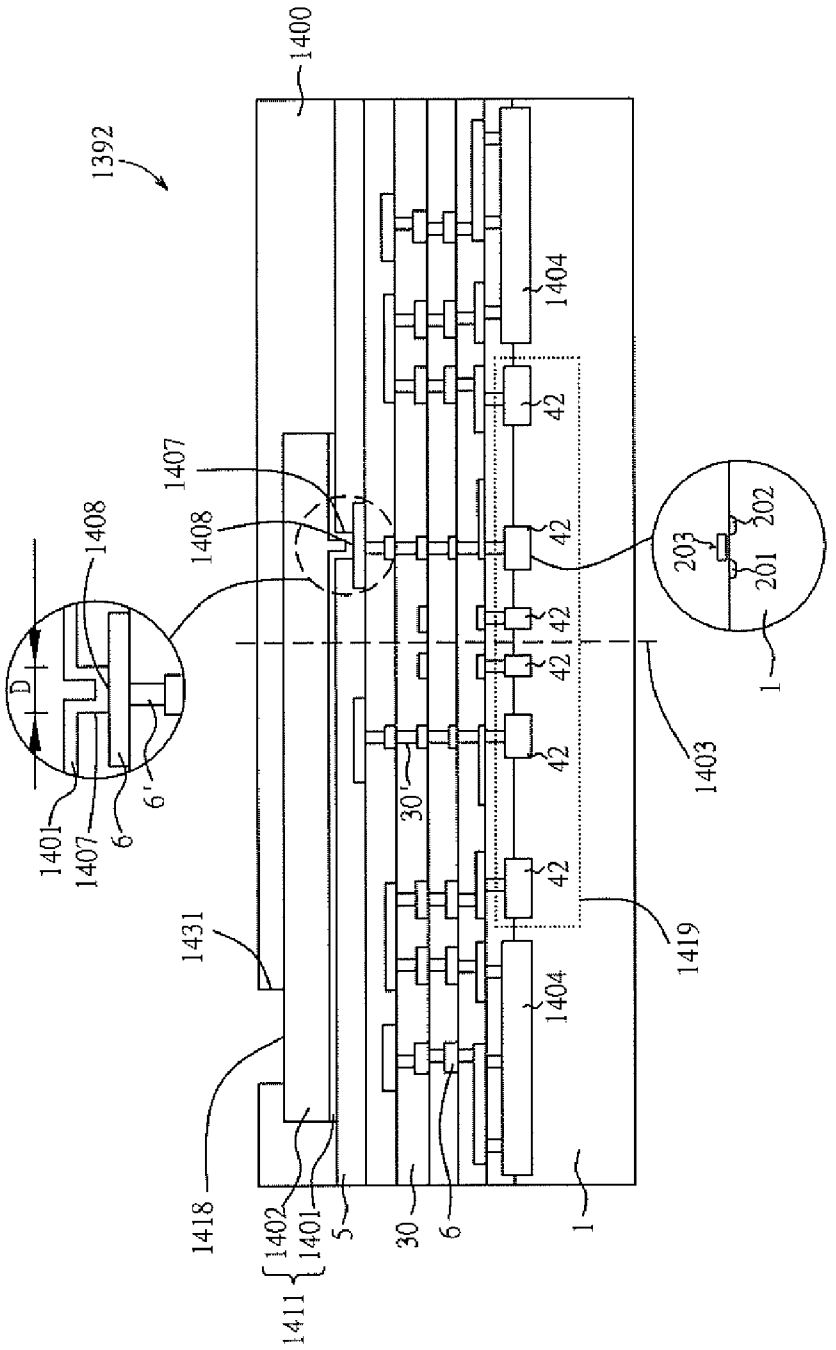

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Fig. 48D

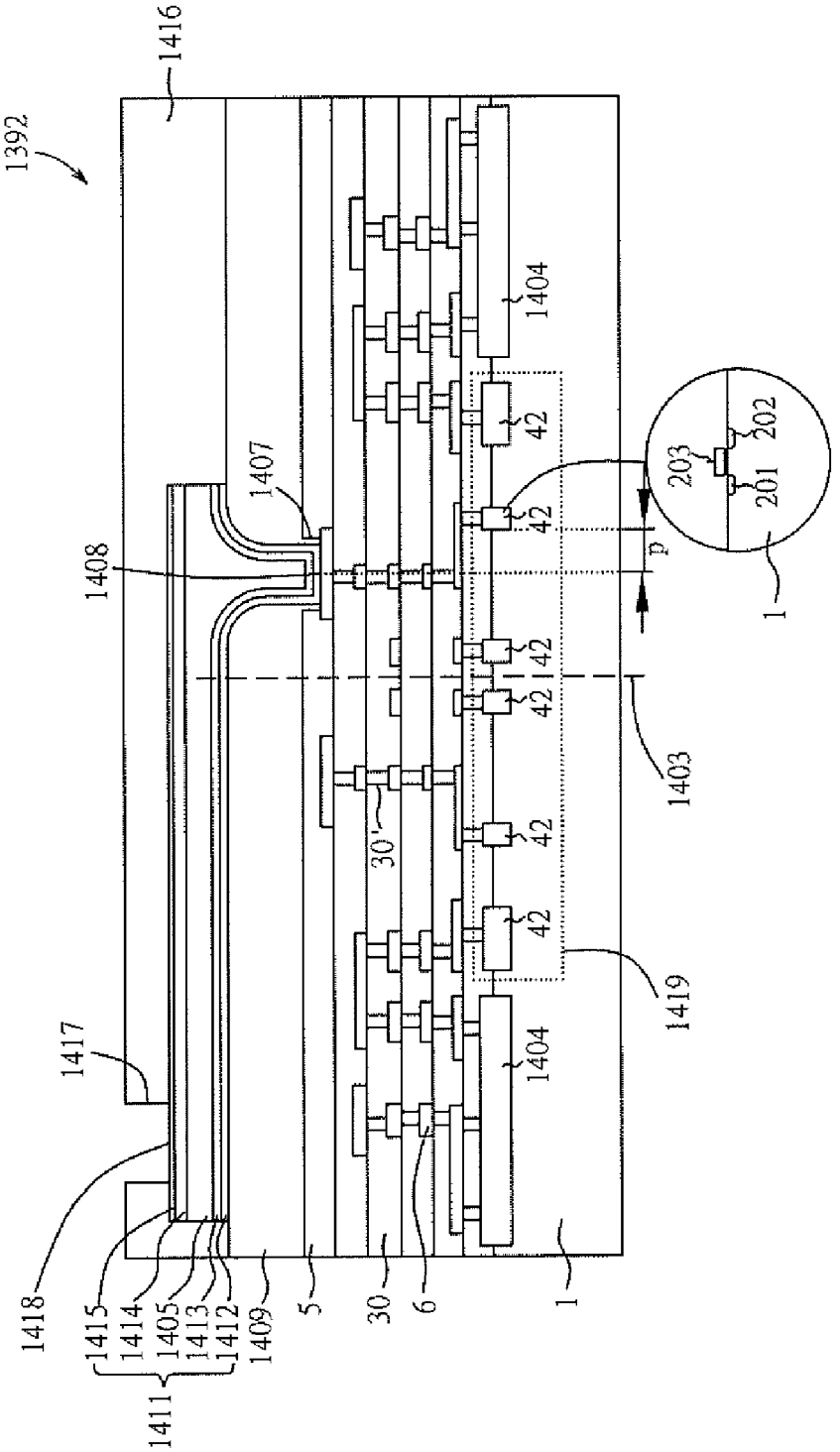

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Fig. 48E

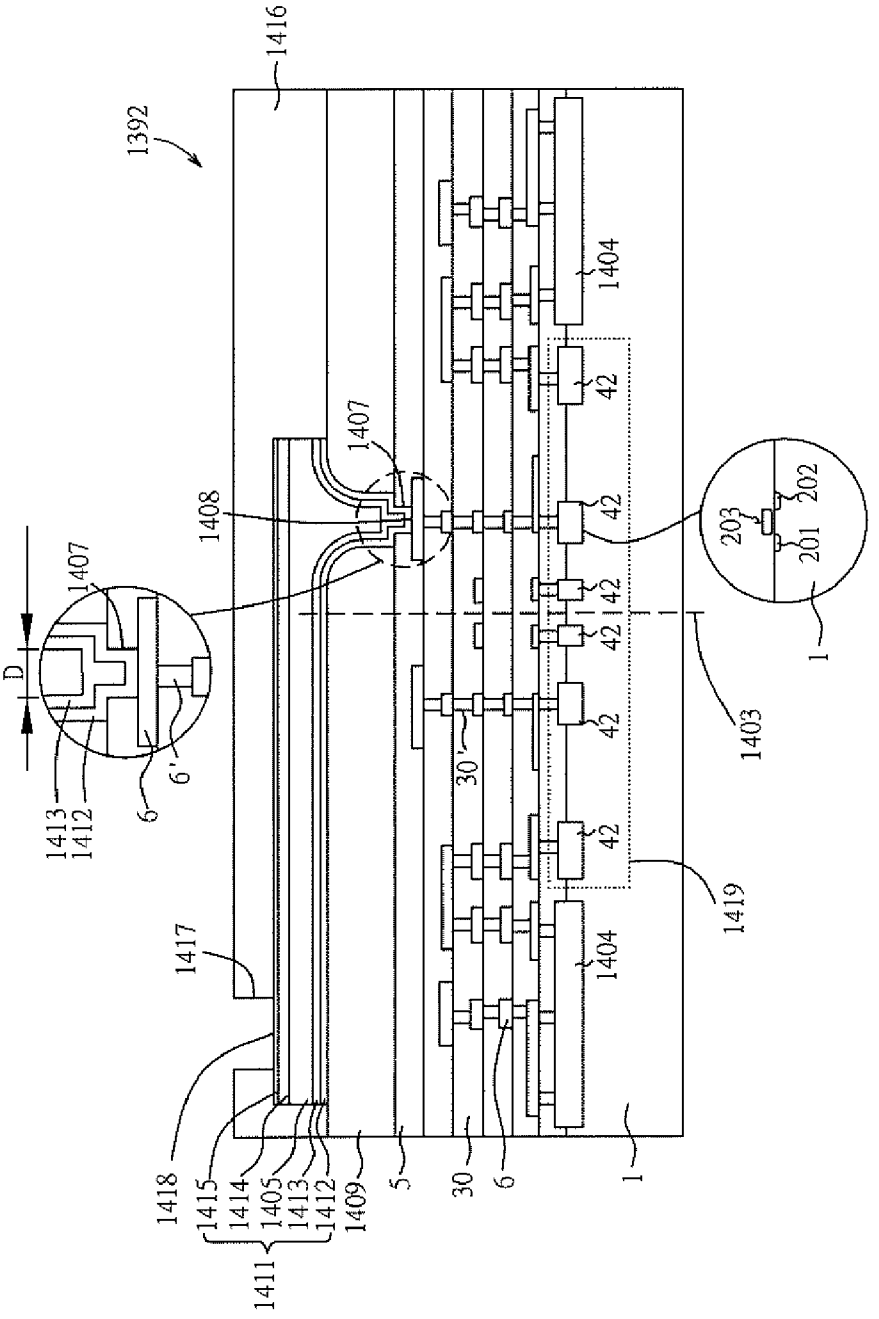

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Fig. 48F

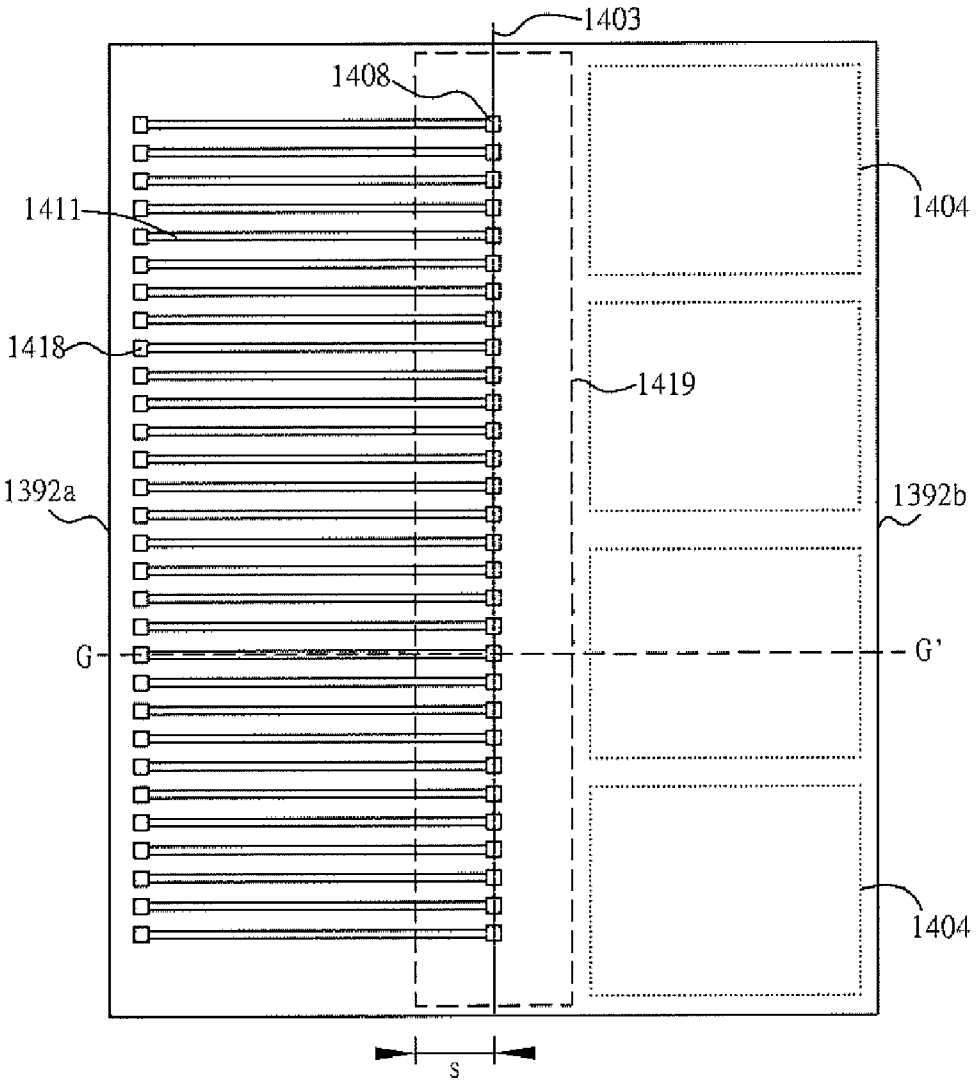


Fig. 48G

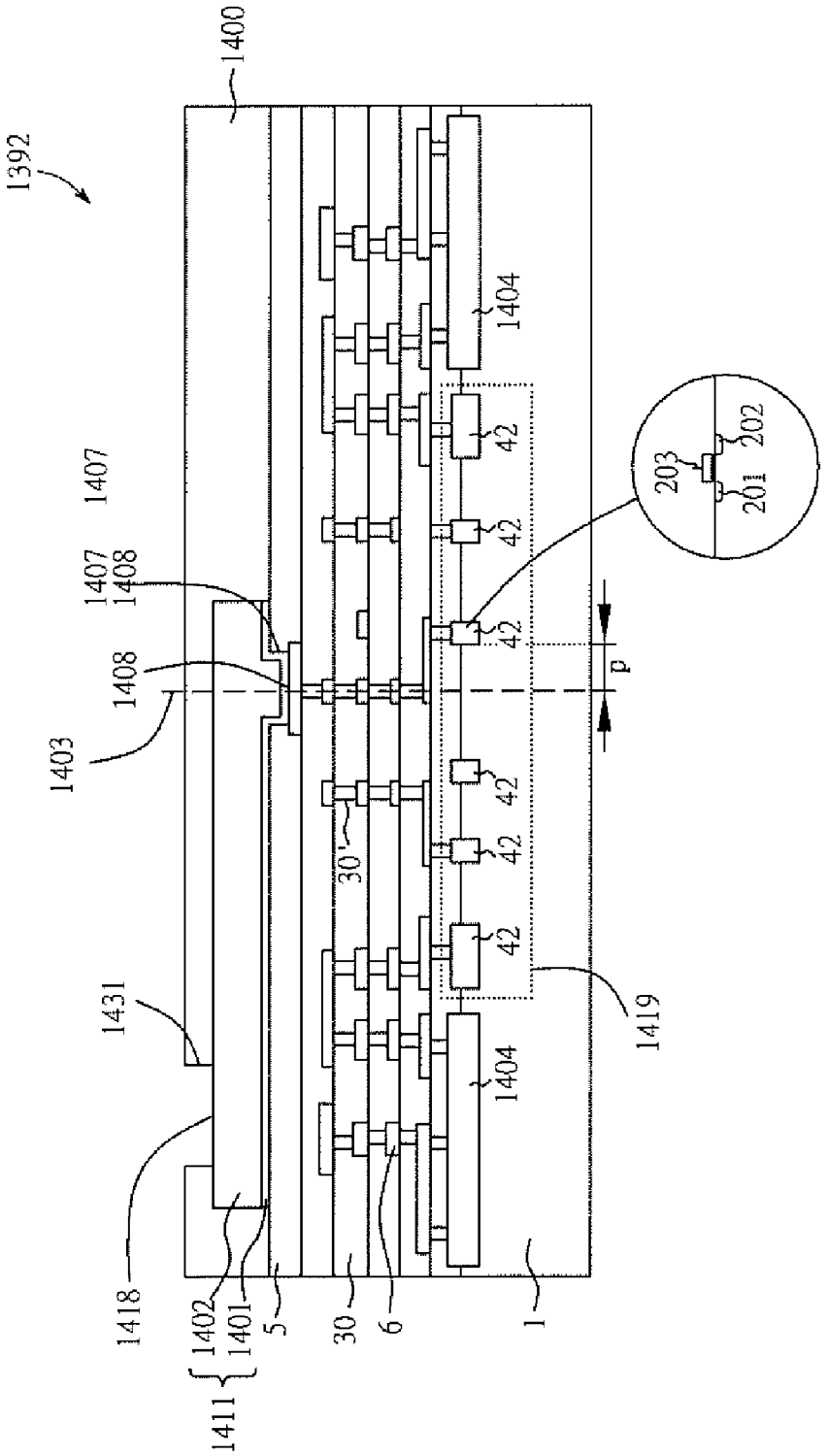

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Fig. 48H

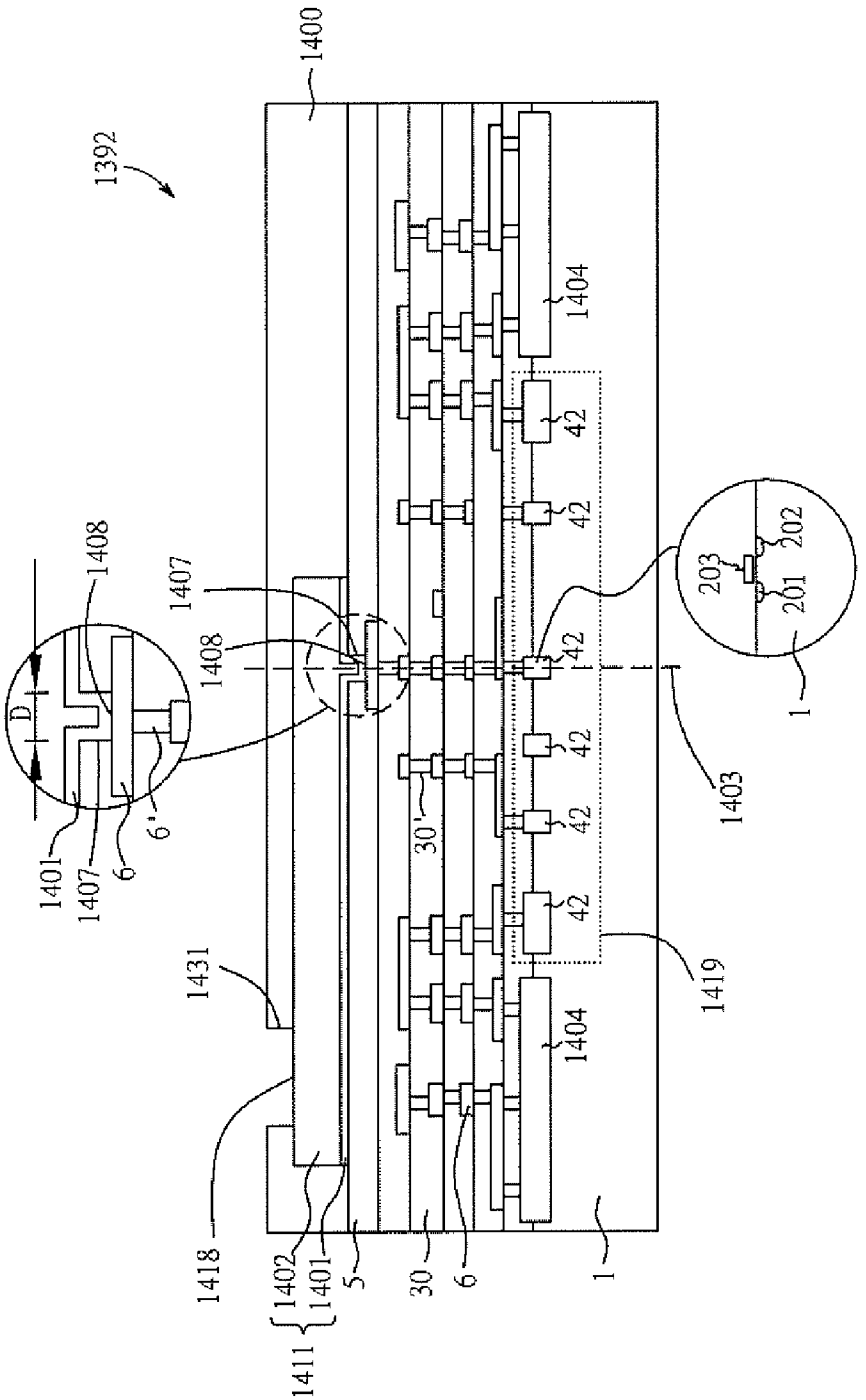

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Fig. 48I

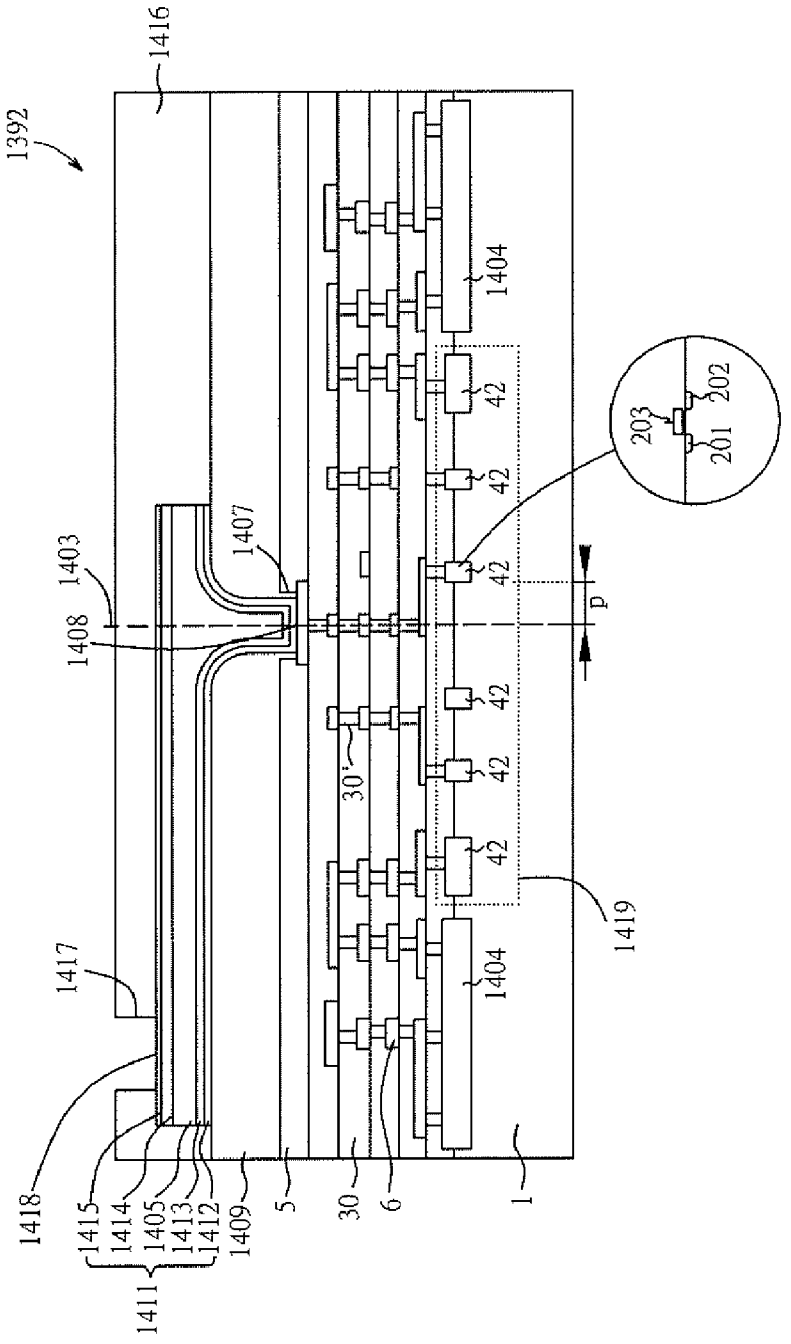

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Fig. 48J

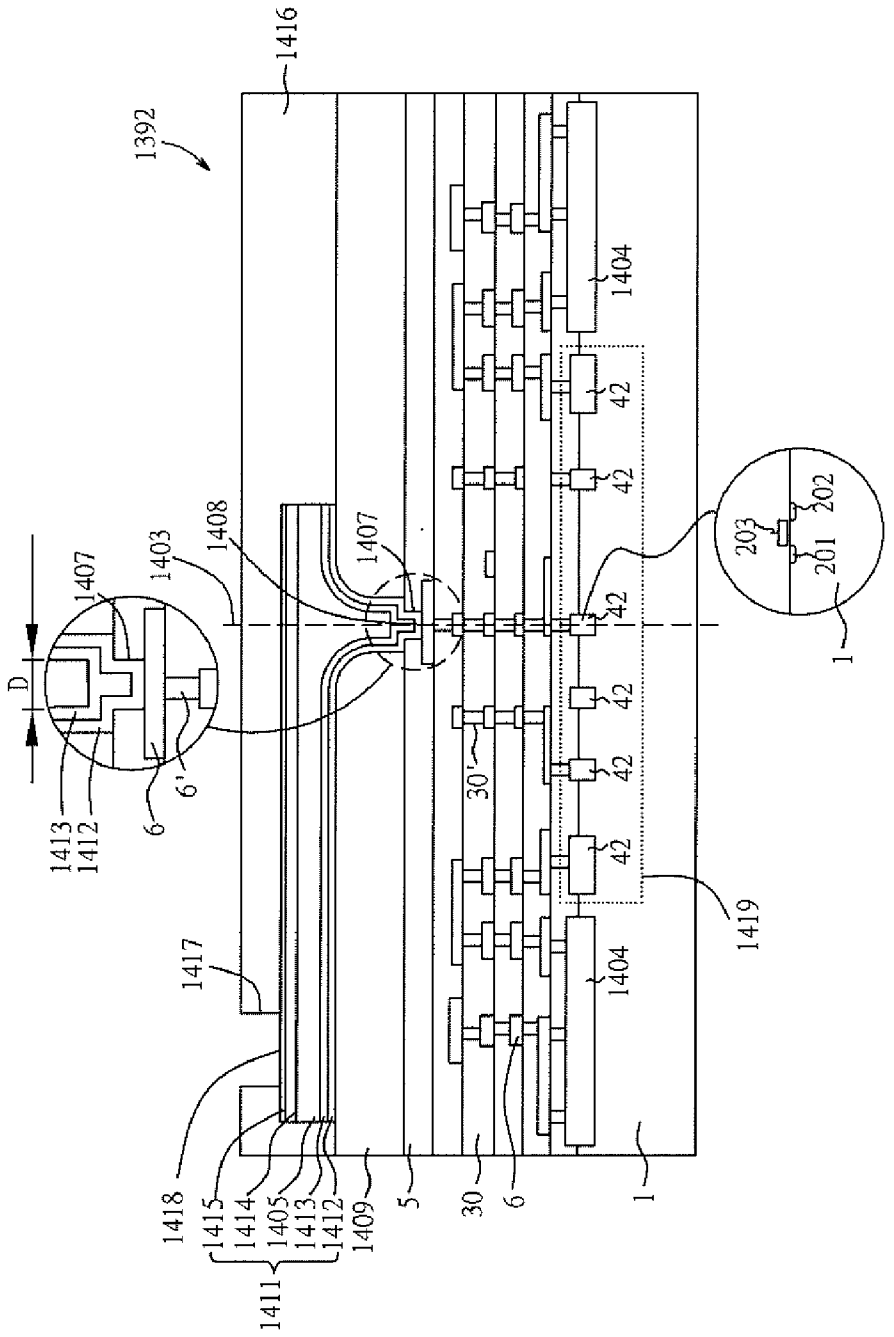

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Fig. 48K

INTEGRATED CIRCUIT CHIP USING TOP POST-PASSIVATION TECHNOLOGY AND BOTTOM STRUCTURE TECHNOLOGY

[0001] This application claims priority to U.S. provisional application No. 61/164,473, filed on Mar. 30, 2009, which is herein incorporated by reference in its entirety.

BACKGROUND OF THE DISCLOSURE

[0002] 1. Field of the Disclosure

[0003] The disclosure relates to integrated circuit chips and chip packages, and more particularly, to integrated circuit chips and packages that utilize differing interconnection schemes for different sides of the circuit chips and packages.

[0004] 2. Brief Description of the Related Art

[0005] Semiconductor chips can be found in many electronic devices, and today many electronic devices are required to run at high speed and/or low power consumption conditions. In traditional semiconductor fabrication, a chip can use wirebonding wires or solder balls bonded with pads, exposed by openings in a passivation layer of the chip, of the chip to connect with a ball grid array (BGA) substrate. Modern electronic systems, modules, and/or circuit boards typically contain many different types of chips, such central processing units (CPUs), digital signal processors (DSPs), analog chips, dynamic random access memory (DRAM) chips, static random access memory (SRAM) chips, flash memory chips, and the like.

[0006] Each chip is typically fabricated using different types and/or different generations of IC manufacturing process technologies. For example, in some notebook personal computers, a CPU chip might be fabricated using a 65 nm IC process technology with a power supply voltage of 1.2V, an analog chip might be fabricated using an older 0.25 micron (250 nm) IC process technology with a power supply voltage of 3.3V, and a DRAM chip might be fabricated using a 90 nm IC process technology at 1.5V, and a flash memory chip might be fabricated using a 0.18 micron (180 nm) IC process technology with power supply voltage at 2.5V.

[0007] Each different type of chip can require a different voltage requirement for its supplied power. For example, a given DRAM chip might require an on-chip voltage converter to convert 3.3V to 1.5V while a flash memory chip might at the same time require an on-chip voltage converter to convert 3.3V to 2.5V. With a variety of supply voltages in a single system, voltage regulation and conversion can be problematic, complicated, and costly.

[0008] Interconnection schemes include the metal connections that connect an IC to other circuit or system components. Such interconnection schemes have become of relative importance and have, with the further miniaturization of the IC, an increasingly negative impact on the circuit performance, including for chip voltage and regulation. For example, the parasitic capacitance and resistance of the metal interconnections increase with smaller scale, which degrades the chip performance significantly. Of significant concern in this respect is the voltage drop along the power and ground buses and the RC delay of the critical signal paths. Attempts to reduce the resistance by using wider metal lines result in higher capacitance of these wires.

[0009] To solve this problem, one approach has been to develop low resistance metal (such as copper) for the wires while low dielectric materials are used in between signal lines. Current practice is to create metal interconnection networks under a layer of passivation, this approach however limits the interconnect network to fine line interconnects and the therewith associated high parasitic capacitance and high line resistivity. The latter two parameters, because of their relatively high values, degrade device performance, an effect which becomes even more severe for higher frequency applications and for long interconnect lines that are, for instance, used for clock distribution lines. Also, fine line interconnect metal cannot carry high values of current that is typically needed for ground busses and for power busses.

SUMMARY OF THE DISCLOSURE

[0010] The present disclosure is directed to integrated circuit chips and chip packages that utilize over-passivation and bottom interconnection schemes (or, "technologies") for the respective major sides of the chip or chip packages.

[0011] An aspect of the present disclosure is directed to chips or chip packages including one interconnection scheme at one side of a chip or chip package and/or another interconnection scheme at another side of a chip or chip package, e.g., an over-passivation scheme at a top of a chip and a bottom scheme at a bottom of the same chip. The integrated circuit chips can be connected to an external circuit or structure, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the over-passivation scheme or the bottom scheme.

[0012] Another aspect of the present disclosure is directed to on-chip voltage-regulating and/or converting devices and circuits.

[0013] Exemplary embodiments of the present disclosure provide chips having an over-passivation scheme at a passivation layer of the chip and a bottom scheme at a backside of a semiconductor substrate of the chip. Exemplary embodiments can include post-passivation schemes for either side of a chip or chip package, e.g., a top of a chip or bottom (backside) of a chip.

[0014] Exemplary embodiments of the present disclosure can provide on-chip voltage-regulating and/or converting devices or circuits that can send electrical power to multiple devices or circuit units (e.g., sub circuits or circuitry portions) requiring different voltage characteristics.

[0015] Furthermore, exemplary embodiments can supply voltage or power to one or more devices or circuit units with little loss due to parasitic effects.

[0016] Further embodiments can provide for the delivery of electrical power to one or more devices or circuit units through a passivation layer and by way of a coarse conductor deposited over the passivation layer.

[0017] Embodiments can further provide an over-passivation metal interconnection that can distribute signals, power, and/or ground output from at least one internal circuit or internal device to at least one other internal circuit or device. Exemplary embodiment can provide for such without connection to ESD, driver, or receiver circuitry.

[0018] Embodiments can further provide an over-passivation metal interconnection that can distribute signals, power, and/or ground output from at least one internal circuit or internal device to at least one other internal circuit or device and/or to external (outside of chip) circuitry, including other chips and chip packages according to the present disclosure.

[0019] These, as well as other components, steps, features, benefits, and advantages of the present disclosure, will now

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become clear from a review of the following detailed description of illustrative embodiments, the accompanying drawings, and the claims.

BRIEF DESCRIPTION OF THE DRAWINGS

[0020] The drawings disclose illustrative embodiments of the present disclosure. They do not set forth all embodiments. Other embodiments may be used in addition or instead. Details that may be apparent or unnecessary may be omitted to save space or for more effective illustration. Conversely, some embodiments may be practiced without all of the details that are disclosed. When the same numeral appears in different drawings, it refers to the same or like components or steps.

[0021] Aspects of the disclosure may be more fully understood from the following description when read together with the accompanying drawings, which are to be regarded as illustrative in nature, and not as limiting. The drawings are not necessarily to scale, emphasis instead being placed on the principles of the disclosure.

[0022] FIG. **1**A is a schematic representation of a prior art voltage regulator or converter circuit connected to multiple internal circuits through a fine-line metallization.

[0023] FIG. **1**B is a schematic representation of a voltage regulator or converter circuit connected to multiple internal circuits through an over-passivation power bus (metal line, trace, or plane), according to an embodiment.

[0024] FIGS. **1**C and **1**D are schematic representation of a voltage regulator or a voltage converter connected to multiple internal circuits through over-passivation power and ground buses (metal lines, traces, or planes), according to an embodiment.

[0025] FIG. **2**A is a top view layout of a prior art voltage regulator or converter circuit connected to multiple internal circuits through a fine-line metallization.

[0026] FIG. **2**B is a top view layout of a voltage regulator or converter circuit connected to multiple internal circuits through an over-passivation power bus (metal line, trace or plane), according to an embodiment.

[0027] FIG. **2**C is a top view layout of a voltage regulator or converter circuit connected to multiple internal circuits through over-passivation power and ground buses (metal lines, traces or planes), according to an embodiment.

[0028] FIG. **3**A is a cross-sectional representation of a prior art voltage regulator or converter circuit connected to multiple internal circuits through a fine-line metallization.

[0029] FIG. **3**B is a cross-sectional representation of a voltage regulator or converter circuit connected to multiple internal circuits through an over-passivation power bus (metal line, trace or bus), according to an embodiment.

[0030] FIG. **3**C is a cross-sectional representation of a voltage regulator or converter circuit connected to multiple internal circuits through over-passivation power and ground buses (metal lines, traces or planes in two patterned circuit metal layers), according to an embodiment.

[0031] FIG. **3**D is a cross-sectional representation of a voltage regulator or converter circuit connected to multiple internal circuits through an over-passivation power bus (metal line, trace or bus), according to an embodiment. This figure is similar to FIG. **3**B except that an additional polymer layer is provided between the bottom-most over-passivation metal layer and the passivation layer.

[0032] FIG. **4** is a schematic representation of an example of a CMOS voltage converter circuit, according to an embodiment.

[0033] FIG. **5**A is a schematic representation of multiple internal circuits connected through a fine-line metallization structure under a passivation layer, according to an embodiment.

[0034] FIG. **5**B is a schematic representation of multiple internal circuits connected through a thick and wide metal layer over a passivation layer to transmit a signal, according to an embodiment.

[0035] FIG. **5**C shows a circuit diagram of an inverter, which can be applied to the internal circuit **21** shown in FIG. **5**B, according to an embodiment.

[0036] FIG. **5**D shows a circuit diagram of an internal driver, which can be applied to the internal circuit **21** shown in FIG. **5**B, according to an embodiment.

[0037] FIG. **5**E shows a circuit diagram of a tri-state buffer, which can be applied to the internal circuit **21** shown in FIG. **5**B, according to an embodiment.

[0038] FIG. **5**F shows a circuit diagram of a tri-state buffer, which can be applied to the internal circuit **21** shown in FIG. **5**B, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0039] FIG. **5**G shows a circuit diagram of a gate switch, which can be applied to the internal circuit **21** shown in FIG. **5**B, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0040] FIG. **5**H shows a circuit diagram of a latch circuit, which can be applied to the internal circuit **21** shown in FIG. **5**B, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0041] FIG. **5**I shows a circuit diagram of a gate switch and internal driver, which can be applied to the internal circuit **21** shown in FIG. **5**B, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0042] FIG. **5**J shows a circuit diagram of a latch circuit and internal driver, which can be applied to the internal circuit **21** shown in FIG. **5**B, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0043] FIG. **5**K is a schematic representation of multiple internal circuits connected through a thick and wide metal layer over a passivation layer to transmit a signal, according to an embodiment.

[0044] FIG. **5**L shows a circuit diagram of an internal receiver, which can be applied to the internal circuit **21** shown in FIG. **5**K, according to an embodiment.

[0045] FIG. **5**M shows a circuit diagram of a tri-state buffer, which can be applied to the internal circuit **21** shown in FIG. **5**K, according to an embodiment.

[0046] FIG. **5**N shows a circuit diagram of a tri-state buffer, which can be applied to the internal circuit **21** shown in FIG. **5**K, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0047] FIG. **50** shows a circuit diagram of a gate switch, which can be applied to the internal circuit **21** shown in FIG. **5**K, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0048] FIG. **5**P shows a circuit diagram of a latch circuit, which can be applied to the internal circuit **21** shown in FIG. **5**K, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0049] FIG. **5**Q shows a circuit diagram of a gate switch and internal receiver, which can be applied to the internal circuit **21** shown in FIG. **5**K, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0050] FIG. **5**R shows a circuit diagram of a latch circuit and internal receiver, which can be applied to the internal circuit **21** shown in FIG. **5**K, connected to a sense amplifier connected to a memory cell, according to an embodiment.

[0051] FIG. **5**S is a schematic representation of multiple internal circuits connected through a thick and wide metal layer over a passivation layer to transmit an analog signal, according to an embodiment.

[0052] FIG. **5**T shows a circuit diagram of a differential amplifier, which can be applied to the internal circuit **21** shown in FIG. **5**S, according to an embodiment.

[0053] FIGS. **5**U-**5**Z show a schematic representation of a memory chip with an address bus and a data bus over a passivation layer, according to an embodiment.

[0054] FIG. **6**A is a top view layout of a distribution of signals from an internal circuit to other internal circuits, according to an embodiment.

[0055] FIG. **6**B is a top view layout of signal distribution, and an internal circuit sends signals to other internal circuits through an over-passivation interconnection scheme, requiring no solder bump and no off-chip circuits, according to an embodiment.

[0056] FIG. **7**A is a cross-sectional representation of a distribution of signals from an internal circuit to other internal circuits, according to an embodiment.

[0057] FIG. **7**B is a cross-sectional representation of signal distribution, and an internal circuit sends signals to other internal circuits through an over-passivation interconnection scheme, requiring no solder bump and no off-chip circuits, according to an embodiment.

[0058] FIG. **7**C is a cross-sectional representation of signal distribution, and an internal circuit sends signals to other internal circuits through an over-passivation scheme, requiring no solder bump and no off-chip circuits, according to an embodiment. Two over-passivation scheme includes two metal layers.

[0059] FIG. **7**D is a cross-sectional representation of signal distribution, and an internal circuit sends signals to other internal circuits through an over-passivation interconnection scheme, according to an embodiment. This figure is similar to FIG. **7**B except that an additional polymer layer is provided between the passivation layer and the bottom-most over-passivation metal layer.

[0060] FIG. **8**A is a schematic representation of a distribution of signals from internal circuits to the external circuits through off-chip circuits using fine-line scheme, according to an embodiment.

[0061] FIGS. **8**B, **8**D, **8**E and **8**F are schematic representations of a signal generated in the internal circuits propagated to an external circuit through over-passivation metals and fine-line metals, and through off-chip circuits, according to an embodiment.

[0062] FIG. **8**C is a schematic representation of a signal transmitted from an external circuit to an internal circuit through over-passivation metals and fine-line metals, and through off-chip circuits, according to an embodiment.

[0063] FIG. **9**A is a top view layout of a distribution of signals from internal circuits to the external circuits through off-chip circuits using a fine-line scheme, according to an embodiment.

[0064] FIGS. **9**B is a top view layout of multiple internal circuits connected to an off-chip circuit through a thick and wide metal trace, bus or plane over a passivation layer, according to an embodiment.

[0065] FIG. **9**C is a top view layout of multiple internal circuits connected to an off-chip circuit through a thick and wide metal trace, bus or plane over a passivation layer, and the off-chip circuit includes two-stage cascade off-chip driver **421**, according to an embodiment.

[0066] FIG. **9**D is a top view layout of multiple internal circuits connected to an off-chip circuit through a thick and wide metal trace, bus or plane over a passivation layer, and the off-chip circuit includes four-stage cascade off-chip driver **42**, according to an embodiment.

[0067] FIG. **10**A is a cross-sectional representation of a distribution of signals from internal circuits to the external circuits through off-chip circuits using fine-line scheme, according to an embodiment.

[0068] FIGS. **10**B-**10**E and **10**G-**10**I are cross-sectional representations of multiple internal circuits connected to an off-chip circuit through a thick and wide metal trace, bus or plane over a passivation layer, according to an embodiment.

[0069] FIG. **10**F is a cross-sectional representation of multiple internal circuits connected to an off-chip circuit through a metal trace, bus or plane under a passivation layer, with a wire wirebonded to a relocated pad on a passivation layer, according to an embodiment.

[0070] FIG. **11**A is a schematic representation of an example of an off-chip driver circuit, which can be applied to the off-chip buffer **42** shown in FIG. **8**B, according to an embodiment.

[0071] FIG. **11**B is a schematic representation of an example of an off-chip receiver circuit, which can be applied to the off-chip buffer **42** shown in FIG. **8**C, according to an embodiment.

[0072] FIG. **11**C is a schematic representation of an example of an off-chip tri-state buffer, which can be applied to the off-chip buffer **42** shown in FIG. **8**B, according to an embodiment.

[0073] FIG. **11**D is a schematic representation of an example of an off-chip driver circuit, which can be applied to the off-chip buffer **42** shown in FIG. **8**E, according to an embodiment.

[0074] FIG. **11**E is a schematic representation of an example of an off-chip tri-state buffer, which can be applied to the off-chip buffer **42** shown in FIG. **8**C, according to an embodiment.

[0075] FIG. **11**F is a schematic representation of an example of an ESD connection, which can be applied to the off-chip ESD circuit **43** shown in FIGS. **8**B, **8**C, **8**E and **8**F, according to an embodiment.

[0076] FIG. **11**G is a schematic representation of an example of a four-stage cascade off-chip driver circuit, which can be applied to the off-chip buffer **42** shown in FIG. **8**F, according to an embodiment.

[0077] FIG. **11**H is a schematic representation of an example of two ESD connections, which can be applied to the off-chip ESD circuit **43** shown in FIG. **8**D, according to an embodiment.

[0078] FIG. **12**A is a schematic representation of a distribution of external power supply to internal circuits, according to an embodiment.

[0079] FIG. **12**B is a schematic representation of distribution of external power supply to internal circuits through over-passivation metals, according to an embodiment. An ESD protection circuit is connected to the over-passivation metals.

[0080] FIG. **12**C is a schematic representation of distribution of external power supply and external ground to internal circuits through over-passivation metals, according to an embodiment. Both power and ground nodes of internal circuits are connected to the over-passivation metals. An ESD circuit is connected to the over-passivation metals.

[0081] FIG. **12**D is a schematic representation of distribution of external power supply and external ground to internal circuits through over-passivation metals, according to an embodiment. More than one ESD circuits are connected to the over-passivation metals.

[0082] FIG. **12**E is a schematic representation of an example of an ESD circuit, which can be applied to the ESD circuit **44** or **45** shown in FIGS. **12**B-**12**D, according to an embodiment.

[0083] FIG. **13**A is a top view layout of a distribution of external power supply to internal circuits, according to an embodiment.

[0084] FIG. **13**B is a top view layout of distribution of external power supply to internal circuits through over-passivation metals, according to an embodiment. An ESD protection circuit is connected to the over-passivation metals.

[0085] FIG. **13**C is a top view layout of distribution of external power supply and external ground to internal circuits through over-passivation, according to an embodiment. Both power and ground nodes of internal circuits are connected to the over-passivation metals. An ESD protection circuit is connected to the over-passivation power and ground traces, buses or planes.

[0086] FIG. **14**A is a cross-sectional representation of a distribution of external power supply to internal circuits, according to an embodiment.

[0087] FIG. **14**B is a cross-sectional representation of distribution of external power supply to internal circuits through over-passivation metals, according to an embodiment. An ESD protection circuit is connected to the over-passivation metals.

[0088] FIG. **14**C is a cross-sectional representation of distribution of external power supply and external ground to internal circuits through over-passivation metals, according to an embodiment. Both power and ground nodes of internal circuits are connected to the over-passivation metals. The power lines, traces or planes are in the second over-passivation metal layer, while the ground lines, traces or planes are in the first over-passivation metal layer under the second over-passivation metal layer. An ESD protection circuit is connected to the over-passivation metals.

[0089] FIG. **14**D is a cross-sectional representation of distribution of external power supply to internal circuits through over-passivation metals, according to an embodiment. An ESD protection circuit is connected to the over-passivation metals. This figure is similar to FIG. **14**B except that an additional polymer layer is formed between the bottom-most over-passivation metal layer and the passivation layer.

[0090] FIG. **15**A and FIG. **15**B are depictions of starting materials, according to an embodiment. The starting materials are wafers. An over-passivation scheme of present disclosure is to be built over the wafer. FIG. **15**B differs from FIG. **15**A in having an optional metal cap over a metal pad or trace exposed by an opening in the passivation layer.

[0091] FIG. **15**C to FIG. **15**L show process steps of forming an over-passivation scheme with two metal layers, with each metal layer being formed by an embossing process, according to an embodiment.

[0092] FIG. **15**M is a cross-sectional view showing a process of forming a semiconductor wafer including an over-passivation scheme at a passivation layer of the semiconductor wafer, according to an embodiment.

[0093] FIG. **16**A to FIG. **16**M show process steps of forming an over-passivation scheme with two metal layers, in which the first over-passivation metal layer is formed by a double-embossing process, while the second over-passivation metal layer is formed by a single-embossing (an embossing) process, according to an embodiment.

[0094] FIG. **17**A to FIG. **17**J show process steps of forming an over-passivation scheme with three metal layers, according to an embodiment. The first and second over-passivation metal layers are formed by a suitable process or processes, e.g., by a double-embossing process, while the third (top-most) over-passivation metal layer is formed by a suitable process or processes, e.g., by a single-embossing (an embossing) process.

[0095] FIG. **18**A to FIG. **18**I show process steps of forming an over-passivation scheme with three metal layers, according to an embodiment. The first and third over-passivation metal layers are formed by a suitable process or processes, e.g., by a single-embossing (an embossing) process, while the second over-passivation metal layer is formed by a suitable process or processes, e.g., by a double-embossing process.

[0096] FIG. **19**A to FIG. **19**I show process steps of forming an over-passivation scheme with two metal layers, according to an embodiment. The first over-passivation metal layer is formed by a suitable process or processes, e.g., by a double-embossing process, while the second (top-most) over-passivation metal layer is formed by a suitable process or processes, e.g., by a single-embossing (an embossing) process.

[0097] FIG. **20** illustrates models for calculating capacitance per unit length for metal lines or traces in the over-passivation scheme and the fine-line scheme, according to an embodiment.

[0098] FIGS. **21** and **22** show top views of a MOS transistor that can be a PMOS transistor or an NMOS transistor, according to an embodiment.

[0099] FIGS. **23**A-**23**M show cross-sectional views for packaging a DRAM chip, according to an embodiment.

[0100] FIG. **23**N shows a top view of a chip package for a DRAM chip, according to an embodiment.

[0101] FIG. **24**A shows a cross-sectional view of a semiconductor wafer, according to an embodiment.

[0102] FIG. **24**B is a cross-sectional view showing a process of thinning a silicon substrate of the semiconductor wafer shown in FIG. **24**A, according to an embodiment.

[0103] FIG. **24**C is a cross-sectional view of the semiconductor wafer, shown in FIG. **24**B, including through-silicon vias in the silicon substrate of the semiconductor wafer and including an insulating layer on sidewalls of the through-silicon vias and on a backside of the silicon substrate, according to an embodiment.

[0104] FIGS. **24**D-**24**H are cross-sectional views showing a process of forming through-silicon vias in the silicon substrate of the semiconductor wafer shown in FIG. **24**B and forming an insulating layer on sidewalls of the through-silicon vias and on a backside of the silicon substrate, according to an embodiment.

[0105] FIGS. **24**I-**24**N are cross-sectional views showing another process of forming through-silicon vias in the silicon substrate of the semiconductor wafer shown in FIG. **24**B and

forming an insulating layer on sidewalls of the through-silicon vias and on a backside of the silicon substrate, according to an embodiment.

[0106] FIGS. **25**A-**25**L are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of the semiconductor wafer shown in FIG. **24**C, according to an embodiment.

[0107] FIGS. **25**M-**25**T are cross-sectional views of semiconductor wafers, according to an embodiment.

[0108] FIGS. **25**U, **25**V and **25**W are cross-sectional views of packages, according to an embodiment.

[0109] FIGS. **26**A-**26**G are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of the semiconductor wafer shown in FIG. **24**C, according to an embodiment.

[0110] FIGS. **26**H-**26**K are cross-sectional views of semiconductor wafers, according to an embodiment.

[0111] FIGS. **27**A-**27**Q are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of the semiconductor wafer shown in FIG. **24**C, according to an embodiment.

[0112] FIGS. **27**R-**27**T are cross-sectional views of semiconductor wafers, according to an embodiment.

[0113] FIGS. **28**A-**28**F are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of the semiconductor wafer shown in FIG. **24**C, according to an embodiment.

[0114] FIGS. **28**G-**28**I are cross-sectional views of semiconductor wafers, according to an embodiment.

[0115] FIG. **28**J is a cross-sectional view of a chip package, according to an embodiment.

[0116] FIGS. **29**A-**29**T show simplified circuit diagrams of semiconductor chips, according to an embodiment.

[0117] FIGS. **30**A-**30**I are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of a semiconductor wafer, according to an embodiment.

[0118] FIGS. **30**J, **30**K and **30**L are cross-sectional views showing a process for forming a semiconductor wafer including an over-passivation scheme at a passivation layer of the semiconductor wafer and a bottom scheme at a backside of the semiconductor wafer, according to an embodiment.

[0119] FIGS. **30**M and **30**N are cross-sectional views showing a process for forming a semiconductor wafer including metal pads, bumps or traces at an active side of a silicon substrate of the semiconductor wafer and including a bottom scheme at a backside of the silicon side, according to an embodiment.

[0120] FIGS. **31**A-**31**G are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of a semiconductor wafer, according to an embodiment.

[0121] FIGS. **31**H and **31**I are cross sectional views showing a process for forming a semiconductor wafer including an over-passivation scheme at a passivation layer of the semiconductor wafer and a bottom scheme at a backside of the semiconductor wafer, according to an embodiment.

[0122] FIG. **31**J is a cross sectional view showing a process for forming a semiconductor wafer including metal pads, bumps or traces at an active side of a silicon substrate of the semiconductor wafer and including a bottom scheme at a backside of the silicon side, according to an embodiment.

[0123] FIGS. **32**A-**32**R are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of a semiconductor wafer, according to an embodiment.

[0124] FIGS. **32**S and **32**T are cross sectional views showing a process for forming a semiconductor wafer including metal pads, bumps or traces at an active side of a silicon substrate of the semiconductor wafer and including a bottom scheme at a backside of the silicon side, according to an embodiment.

[0125] FIG. **32**U is a cross sectional view showing a process for forming a semiconductor wafer, according to an embodiment.

[0126] FIGS. **33**A-**33**K are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of a semiconductor wafer, according to an embodiment.

[0127] FIG. **33**L is a cross sectional view showing the semiconductor wafer illustrated in FIG. **33**K with an over-passivation scheme at an active side of a silicon substrate of the semiconductor wafer, according to an embodiment.

[0128] FIG. **33**M is a cross sectional view showing the semiconductor wafer illustrated in FIG. **33**K with metal pads, bumps or traces at an active side of a silicon substrate of the semiconductor wafer, according to an embodiment.

[0129] FIGS. **33**N-**33**S are cross-sectional views showing a process for forming a bottom scheme of a bottom structure technology at a backside of a semiconductor wafer, according to an embodiment.

[0130] FIGS. **33**T and **33**U are cross sectional views of semiconductor wafers, according to an embodiment.

[0131] FIG. **33**V shows a top view of a capacitor of a semiconductor wafer, according to an embodiment.

[0132] FIG. **33**W shows a cross sectional view cut along the dot line A-A in FIG. **33**V, according to an embodiment.

[0133] FIG. **33**X shows a top view of a capacitor of a semiconductor wafer, according to an embodiment.

[0134] FIG. **33**Y shows a cross sectional view cut along the dot line A-A in FIG. **33**X, according to an embodiment.

[0135] FIGS. **34**A-**34**G are cross sectional views showing a process of forming a super capacitor, a patterned circuit layer, metal bumps or pillars and two polymer layers at passivation layer of a semiconductor wafer, according to an embodiment.

[0136] FIGS. **35**A-**35**D are cross sectional views showing a process of forming a semiconductor wafer including an over-passivation scheme at a passivation layer of the semiconductor wafer and including a bottom scheme, a discrete inductor and a discrete capacitor at a backside of the semiconductor wafer, according to an embodiment.

[0137] FIGS. **36**A-**36**D are cross sectional views of chip-package modules, according to an embodiment.

[0138] FIGS. **37**A-**37**D and **38**A-**38**D are cross sectional views of modules, according to an embodiment.

[0139] FIGS. **39**A, **39**H, **39**I and **39**J are circuit diagrams each showing interface circuits of a cache memory chip and a chip, according to an embodiment.

[0140] FIGS. **39**B and **39**C show circuit diagrams of inter-chip circuits in a cache memory chip, according to an embodiment.

[0141] FIGS. **39**D and **39**E show circuit diagrams of inter-chip circuits in a chip, according to an embodiment.

[0142] FIGS. **39**F and **39**G show circuit diagrams of off-chip buffers in a chip, according to an embodiment.

[0143] FIGS. **40**A-**40**F show how to calculate an active area of an ESD unit of a chip and define a size of an ESD circuit composed of one or more the ESD units, according to an embodiment.

[0144] FIG. **41** shows a cross sectional view of a module including a substrate, a radio frequency (RF) module, and a wirebonded stacked memory BGA package, according to an embodiment.

[0145] FIGS. **42**A-**42**O are cross-sectional views showing a process for forming a chip, according to an embodiment.

[0146] FIGS. **43**A-**43**E are cross-sectional views showing a process for forming a semiconductor wafer finalized to be cut into a plurality of a cache memory chip, according to an embodiment.

[0147] FIGS. **44**A-**44**C are cross-sectional views showing a process for bonding the chip shown in FIG. **42**N with the semiconductor wafer shown in FIG. **43**D, according to an embodiment.

[0148] FIGS. **45**A and **45**B are circuit diagrams each showing interface circuits of a cache memory chip and a chip, according to an embodiment.

[0149] FIGS. **46**A-**46**N are cross-sectional views showing a process for forming a semiconductor wafer finalized to be cut into a plurality of a cache memory chip, according to an embodiment.

[0150] FIGS. **47**A-**47**C are cross-sectional views showing a process for forming a processor unit, according to an embodiment.

[0151] FIGS. **47**D-**47**F are cross-sectional views showing a process for forming a processor unit, according to an embodiment.

[0152] FIGS. **47**G-**47**I are cross-sectional views showing a process for forming a processor unit, according to an embodiment.

[0153] FIGS. **47**J-**47**L are cross-sectional views showing a process for forming a processor unit, according to an embodiment.

[0154] FIG. **48**A shows another stacked DRAM BGA package **1390**, according to an embodiment.

[0155] FIG. **48**B shows a top view of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A, according to an embodiment.

[0156] FIGS. **48**C and **48**D show cross-sectional views of various types of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of F-F' of FIG. **48**B, and the redistribution circuit layer **1411** is made mainly of sputtered aluminum, according to an embodiment.

[0157] FIGS. **48**E and **48**F shows cross-sectional views of various types of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of F-F' of FIG. **48**B, and the redistribution circuit layer **1411** is made mainly of electroplated copper or gold, according to an embodiment.

[0158] FIG. **48**G shows a top view of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A, according to an embodiment.

[0159] FIGS. **48**H and **481** show cross-sectional views of various types of a DRAM chip **1392** placed, assembled, or incorporated in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of G-G' of FIG. **48**G, and the redistribution circuit layer **1411** is made mainly of sputtered aluminum, according to an embodiment.

[0160] FIGS. **48**J and **48**K shows cross-sectional views of various types of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of G-G' of FIG. **48**G, and the redistribution circuit layer **1411** is made mainly of electroplated copper or gold, according to an embodiment.

[0161] While certain embodiments are depicted in the drawings, one skilled in the art will appreciate that the embodiments depicted are illustrative and that variations of those shown, as well as other embodiments described herein, may be envisioned and practiced within the scope of the present disclosure.

DETAILED DESCRIPTION OF THE DISCLOSURE

[0162] Illustrative embodiments are now discussed. Other embodiments may be used in addition or instead. Details that may be apparent or unnecessary may be omitted to save space or for a more effective presentation. Conversely, some embodiments may be practiced without all of the details that are disclosed.

[0163] The present disclosure provides for integrated circuit chips and chip packages that utilize over-passivation and bottom interconnection schemes (or, "technologies") for the respective major sides of the chip or chip packages.

[0164] An aspect of the present disclosure is directed to chips or chip packages including one interconnection scheme at one side of a chip or chip package and/or another interconnection scheme at another at another side of a chip or chip package, e.g., an over-passivation scheme at a top of a chip and a bottom scheme at a bottom of the same chip.

[0165] Another aspect of the present disclosure is directed to on-chip voltage-regulating and/or converting devices and circuits. Such on-chip voltage regulators and converters can provide a constant voltage source for semiconductor devices located at different locations on an IC chip through on-chip power/ground buses. The voltage can be provided with minimized/reduced parasitic loss, minimized/reduced energy consumption, and/or minimized/reduced ripple effect.

[0166] FIGS. **1**A, **2**A, and **3**A show a circuit diagram, a top view and a cross-sectional view, respectively, of a prior art chip structure useful for discussing embodiments of the present disclosure. The voltage regulator or converter circuit **41** receives an external power voltage Vdd, outputs a power voltage Vcc, and delivers the power Vcc to the internal circuits **20**, including **21**, **22**, **23** and **24**, using IC fine-line metal traces **6191** and **61** under a passivation layer **5**. The IC fine-line metal traces **61** include segments of **618**, **6111**, **6121***a*, **6121***b*, **6121***c* and **6141**. The fine-line metal traces **6191** and **61** are under the passivation layer **5**.

[0167] Exemplary embodiments of the present disclosure are described below.

First Embodiment: Over-Passivation Power/Ground Buses with a Voltage Regulator-Converter

[0168] FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C, and **3**D illustrate a first exemplary embodiment of the present disclosure. FIGS. **1**B and **1**C show a simplified circuit diagram where metal traces **81** and/or **82** over a passivation layer **5** connect a voltage regulator or converter circuit **41** and internal circuits **21**, **22**, **23** and **24** to distribute a power voltage or a ground reference voltage, and a dotted line **5** indicates a passivation layer, coarse traces indicate traces of an over-passivation

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scheme **102** formed over the passivation layer **5**, and fine traces indicate traces formed under the passivation layer **5**. FIGS. **2**B and **2**C show top views of semiconductor chips realizing the circuitry shown in FIGS. **1**B and **1**C, respectively, and coarse traces mean the traces of the over-passivation scheme **102** formed over the passivation layer **5**, and fine traces mean the traces formed under the passivation layer **5**. FIGS. **3**B and **3**C show cross-sectional views of semiconductor chips realizing the circuitry shown in FIGS. **1**B and **1**C, respectively. FIGS. **2**B and **2**C show top views of the semiconductor chips shown in FIGS. **3**B and **3**C, respectively. The over-passivation scheme **102** shown in FIG. **3**B includes a polymer layer **99** and two metal traces **81** and **81**P provided by a patterned circuit layer **811**, and an opening **9919** in the polymer layer **99** is over a contact point **8110** of the metal trace **81**P and exposes it. The over-passivation scheme **102** shown in FIG. **3**C includes a metal traces **81** provided by a patterned circuit layer **812**, a metal trace **82** provided by a patterned circuit layer **821**, and two polymer layers **98** and **99**, and an opening **9929** in the polymer layer **99** is over a contact point **8120** of the patterned circuit layer **812** and exposes it. The over-passivation scheme **102** shown in FIG. **3**D includes two polymer layers **95** and **99** and two metal traces **81** and **81** P provided by the patterned circuit layer **811**, and multiple openings **9519**, **9519'**, **9511**, **9512** and **9514** are in the polymer layer **95**, and an opening **9919** in the polymer layer **99** is over a contact point **8110** of the metal trace **81**P and exposes it.

[0169] For embodiments of the present disclosure, an on-chip voltage regulator or converter circuit **41** is configured to send electrical power to several internal devices **21**, **22**, **23** and **24** (or circuits), and the voltage regulator or converter circuit **41** and the internal devices **21**, **22**, **23** and **24** are formed in and/or on a silicon substrate **1** within a same IC chip. Through openings **511**, **512** and **514** in a passivation layer **5**, and by way of a coarse metal conductor **81** deposited over the passivation layer, electrical power output from the voltage regulator or converter circuit **41** is delivered to several devices or circuit units **21**, **22**, **23** and **24** with little loss or parasitic effects. The advantage of this design is that, affiliated with the regulated power source and with the coarse metal conductor, the voltage to the next level at the load of internal circuits can be controlled at a voltage level with high precision. When the reference number of **41** is a voltage regulator, the output voltage Vcc of the voltage regulator **41** is within +10% and −10% of the desired voltage level, and exemplary within +5% and −5% of the desired voltage level, insensitive to voltage surge or large fluctuation at the input node connected with an external power supply Vdd input from the power metal trace **81**P. Alternatively, the voltage regulator **41** may have an output node at a voltage level of Vcc output from the voltage regulator **41** and an input node at a voltage level of Vdd supplied from an external circuit, and a ratio of a difference of the voltage level of Vdd minus the voltage level of Vcc to the voltage level of Vdd is less than 10%. Hence, circuit performance can be improved. The voltage regulator **41** may have an output of between **1** volt and **10** volts, and exemplary between 1 volt and 5 volts.

[0170] In some applications, if the chip requires a voltage level Vcc different from the voltage level Vdd of the external power supply, a voltage converter may be installed in the chip. The reference number of **41** may indicate the voltage converter. The on-chip voltage converter **41**, in addition to the voltage regulating circuit, is desirable in this case to convert the voltage level Vdd of the external power supply to the voltage level Vcc required in the chip. The converter may output a voltage level Vcc higher than the voltage Vdd at the input node. Alternatively, the converter may output a voltage level Vcc lower than the voltage Vdd at the input node. The voltage converter may have an output of between 1 volt and 10 volts, and exemplary between 1 volt and 5 volts. When the voltage level of Vcc ranges from 0.6 volts to 3 volts, the voltage level of Vdd ranges from 3 volts to 5 volts. When the voltage level of Vcc ranges from 0.6 volts to 2 volts, the voltage level of Vdd ranges from 2 volts to 3 volts. For example, when the voltage level of Vcc is 2.5 volts, the voltage level of Vdd is 3.3 volts. When the voltage level of Vcc is 1.8 volts, the voltage level of Vdd is 3.3 volts. When the voltage level of Vcc is 1.8 volts, the voltage level of Vdd is 2.5 volts. When the voltage level of Vcc is 3.3 volts, the voltage level of Vdd is 5 volts.

[0171] FIG. **1**B shows circuit schematics of exemplary embodiments of the present disclosure. As shown, the voltage regulator or converter circuit **41** receives a voltage Vdd from an external power supply, and outputs a voltage Vcc for the internal circuits **20**, including **21**, **22** **23**, and **24**. The output voltage Vcc at node P is distributed to the power nodes Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24**, respectively, first up through a passivation opening **519'** in the passivation layer **5**, then through a thick metal trace **81** over the passivation layer **5**, then down through the passivation openings **511**, **512**, and **514** in the passivation layer **5**, and then through the fine-line metal traces **61'** to the internal circuits **20**: particularly through the segment **611** of the fine-line metal traces **61'** to the internal circuit **611**; particularly through the segments **612***a* and **612***b* of the fine-line metal traces **61'** to the internal circuit **22**; particularly through the segments **612***a* and **612***c* of the fine-line metal traces **61'** to the internal circuit **23**; and through the segment **614** of the fine-line metal traces **61'** to the internal circuit **24**.

[0172] Each of the internal circuits **20**, including **21**, **22**, **23** and **24**, includes at least a PMOS transistor having a source connected to the fine-line metal traces **61'**, for example. Each of the internal circuits **20**, including **21**, **22**, **23** and **24**, may include a NMOS transistor having a ratio of a physical channel width thereof to a physical channel length ranging from, e.g., about 0.1 and 20, ranging from, e.g., about 0.1 and 10 or preferably ranging from, e.g., about 0.2 and 2. Alternatively, each of the internal circuits **20**, including **21**, **22**, **23** and **24**, may include a PMOS transistor having a ratio of a physical channel width thereof to a physical channel length ranging from, e.g., about 0.2 and 40, ranging from, e.g., about 0.2 and 40 or preferably ranging from, e.g., about 0.4 and 4.

[0173] The chip structure in FIG. **1**B can utilize a coarse metal conductor **81** as a carrier of the power/ground lines, traces, or planes. In this case, the voltage drop and noise is much reduced since the coarse metal conductor **81** has lower resistance and capacitance than the fine-line metal traces.

[0174] The internal circuits, or internal circuit units **20**, shown in all of the embodiments, include two NOR gates **22** and **24**, one NAND gate **23**, and one internal circuit **21**, for example. The internal circuits **20**, **21**, **22**, **23**, and **24** can be any type of IC circuits, such as NOR gate, NAND gate, AND gate, OR gate, operational amplifier, adder, multiplexer, diplexer, multiplier, A/D converter, D/A converter, CMOS transistor, bipolar CMOS transistor or bipolar circuit. The NOR gate **22** or **24** or NAND gate **23** has three input nodes Ui, Wi or Vi, one output node Uo, Wo or Vo, one Vcc node Up, Wp

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or Vp, and one Vss node Us, Ws or Vs. The internal circuit **21** has one input node Xi, one output node Xo, one Vcc node Tp and one Vss node Ts. Each of the internal circuits or internal circuit units **20**, including **21**, **22**, **23**, and **24**, usually has signal nodes, power nodes, and ground nodes.

[0175] FIGS. **2**B and **3**B provide the top view and cross-sectional view, respectively, of the circuit diagram shown in FIG. **1**B. It is noted that, in FIG. **3**B, the fine-line metal structures **611**, **612**, **614**, **619** and **619'** can be composed of stacked fine-line metal pads **60** and via plugs **60'** filled in the vias **30'**. The upper vias **30'** are substantially aligned with the lower ones; the upper fine-line metal pads **60** are substantially aligned with the lower ones; the upper via plugs **60** are substantially aligned with the lower ones. Referring to FIGS. **1**B, **2**B and **3**B, the fine-line metal traces or plane **612** includes multiple portions **612***a*, **612***b* and **612***c*, and is used for the local power distribution.

[0176] The thick metal traces or plane **81** over the passivation layer **5** is used for global power distribution and connects the fine-line metal traces or plane **619'**, **611**, **612** and **614**. The thick metal trace or plane **81** over the passivation layer **5**, shown in FIGS. **1**B and **2**B, may be composed of only one patterned circuit layer **811**, as shown in FIG. **3**B, or multiple patterned circuit layers, not shown. The patterned circuit layer **811**, such as a power plane, bus, trace or line, to distribute a power voltage Vcc is realized from the concept of the coarse trace **81** shown in FIGS. **1**B and **2**B. When the thick metal traces or plane **81** over the passivation layer **5**, shown in FIG. **2**, is composed of multiple patterned circuit layers, a polymer layer, such as polyimide (PI), benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, may be between the neighboring patterned circuit layers, separating the patterned circuit layers. A polymer layer **99**, such as polyimide (PI), benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, may be on the topmost one of the patterned circuit layers, separated by the above mentioned polymer layers, over the passivation layer, not shown, or on the only one patterned circuit layer **811**, as shown in FIGS. **3**B and **3**D. Alternatively, A polymer layer **95**, such as polyimide (PI), benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-**8**, elastomer or silicone, may be between the passivation layer and the bottommost one of the patterned circuit layers, separated by the above mentioned polymer layers, not shown, or between the passivation layer **5** and the only one patterned circuit layer **811**, as shown in FIG. **3**D. The polymer layer **95** may have a thickness larger than 2 micrometers, such as between 2 and 30 micrometers. Multiple openings **9519**, **9519'**, **9511**, **9512** and **9514** in the polymer layer **95** are substantially aligned with the openings **519**, **519'**, **511**, **512** and **514** in the passivation layer **5**, respectively. The openings **9519**, **9519'**, **9511**, **9512** and **9514** in the polymer layer **95** expose the pads (including **6190** and **6190'**) exposed by the openings **519**, **519'**, **511**, **512** and **514** in the passivation layer **5**, respectively.

[0177] Some openings **9519** and **9519'** in the polymer layer **95** have lower portions having widths or transverse dimensions smaller than those of the openings **519** and **519'** in the passivation layer **5** aligned with the openings **9519** and **9519'**, respectively. The polymer layer **95** covers a portion of the pads **6190** and **6190'** exposed by the openings **519** and **519'** in the passivation layer **5**. The shape of the openings **519** and **519'** from a top perspective view may be round, square, rectangular or polygon. If the openings **519** and **519'** are round, the openings **519** and **519'** may have a diameter of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.5 and 30 microns. If the openings **519** and **519'** are square, the openings **519** and **519'** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **519** and **519'** are rectangular, the openings **519** and **519'** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns, and a length of between 1 micron and 1 centimeter. If the openings **519** and **519'** are polygon having more than five sides, the openings **519** and **519'** have a largest diagonal length of between 0.1 and 200 microns, between 0.5 and 100 microns, or, preferably, between 0.1 and 30 microns. Alternatively, the openings **519** and **519'** have a largest transverse dimension of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. In a case, the openings **519** and **519'** have a width of between 30 and 100 microns, with the lower portion of the openings **9519** and **9519'** in the polymer layer **95** having a width of between 20 and 100 microns.

[0178] Some openings **9511**, **9512** and **9514** in the polymer layer **95** have lower portions having widths or transverse dimensions larger than those of the openings **511**, **512** and **514** in the passivation layer **5** aligned with the openings **9511**, **9512** and **9514**, respectively. The openings **9511**, **9512** and **9514** in the polymer layer **95** further expose the passivation layer **5** close to the openings **511**, **512** and **514**. The shape of the openings **511**, **512** and **514** from a top perspective view may be round, square, rectangular or polygon. If the openings **511**, **512** and **514** are round, the openings **511**, **512** and **514** may have a diameter of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.5 and 30 microns. If the openings **511**, **512** and **514** are square, the openings **511**, **512** and **514** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **511**, **512** and **514** are rectangular, the openings **511**, **512** and **514** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns, and a length of between 1 micron and 1 centimeter. If the openings **511**, **512** and **514** are polygon having more than five sides, the openings **511**, **512** and **514** have a largest diagonal length of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. Alternatively, the openings **511**, **512** and **514** have a largest transverse dimension of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. In a case, the openings **511**, **512** and **514** have a width of between 5 and 30 microns, with the lower portion of the openings **9511**, **9512** and **9514** in the polymer layer **95** having a width of between 20 and 100 microns.

[0179] The previous description concerning the openings **519**, **519'**, **511**, **512** and **514** in the passivation layer **5** and the openings **9519**, **9519'**, **9511**, **9512** and **9514** in the polymer layer **95** can be applied to the embodiments shown in **15**A-**15**L, **16**A-**16**M, **17**A-**17**J, **18**A-**18**I and **19**A-**19**I.

[0180] One of the patterned circuit layers, such as **811** shown in FIGS. **3**B and **3**D, composing the thick metal trace or plane **81** over the passivation layer **5** may include an adhesion/barrier/seed layer **8111**, and a bulk conduction metal layer **8112**. The methods to form the patterned circuit layer **811** and the specification thereof may follow the methods to form the patterned circuit layer **801**, **802** or **803** and the

specification thereof shown in FIGS. **15**A-**15**M, **16**A-**16**M, **17**A-**17**J, **18**A-**18**I and **19**A-**19**I.

[0181] In FIGS. **1**B, **2**B and **3**B, an external power supplies a voltage level Vdd at a metal pad **8110** connected to a metal pad **6190** of a topmost one of fine-line circuit metal layers **619** under the passivation layer **5** through an opening **519** in the passivation layer **5**, and inputs to the voltage regulator or converter circuit **41**. The voltage regulator or converter circuit **41** outputs a power voltage to supply the internal circuits **21**, **22**, **23** and **24** through the fine-line

[0182] Attorney Docket: **085027-0676** circuit metal layers **619'**, thick patterned trace or plane **811** and fine-line circuit metal layers **611**, **612** and **614**. The fine-line circuit layers **619**, **619'**, **611**, **612** and **614** are separated by thin-film insulating layers **30**, such as silicon oxide.

[0183] Though FIG. **3**B shows only one patterned circuit layer **81** for distributing a regulated or converted power voltage of Vcc, multiple patterned circuit layers with one or more polymer layers deposited there between can be formed over the passivation layer **5** and used to distribute a regulated or converted power voltage of Vcc. Metal traces or planes in different patterned circuit layers are connected through the openings in the polymer layer there between.

[0184] FIGS. **1**A, **2**A and **3**A reveal the external power supply at a voltage level Vdd inputs the voltage regulator or converter circuit **41** through the pad **6190** exposed by the opening **519** in the passivation layer **5** and through the fine-line circuit layers **619** (including stacked fine-line metal pads and vias). The output power at voltage level Vcc outputs from the voltage regulator or converter circuit **41** is distributed to supply the voltage of Vcc to the internal circuits **21**, **22**, **23** and **24** only through IC fine line interconnection **61** including segments **6191'**, **618**, **6111**, **6121** and **6141**.

[0185] In FIGS. **1**B, **2**B, **3**B and **3**D, the ground voltage is denoted as Vss without detailing the circuit schematics, layout and structure for distributing the ground voltage. FIGS. **1**C, **2**C and **3**C describe the circuit schematics, top view and cross-sectional view, respectively, showing the thick metal traces or planes **81** and **82** over the passivation layer **5** for distributing both of the power supply voltage of Vcc and the ground reference voltage of Vss. The structure **82** of distributing the ground reference voltage of Vss is similar to the above mentioned structure **81** of distributing the power supply voltage of Vcc, except that a common ground voltage Vss is provided for the voltage regulator or converter circuit **41** and the internal circuits **21**, **22**, **23** and **24** through the thick metal trace or plane **82**. That means the external ground node Es may be connected to the ground node Rs of the voltage regulator or converter circuit **41** and to the internal ground node Ts, Us, Vs, Ws of the internal circuits **21**, **22**, **23** and **24**: In FIGS. **1**C, **2**C and **3**C, the point Es connected to a ground source of an external circuitry at a voltage level Vss is connected to (1) the ground node Rs of the voltage regulator or converter circuit **41** through an opening **529** in the passivation layer **5**, and (2) the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the thick metal lines, buses or traces **82** over the passivation layer **5**, the openings, **521**, **522** and **524** in the passivation layer **5**, and fine-line metal structures **621**, **622** (including **622***a*, **622***b* and **622***c*) and **624**.

[0186] FIG. **3**C shows two patterned circuit layers **812** and **821** over the passivation layer **5**, used for distributing a power voltage Vcc and a ground reference voltage Vss, respectively. The bottom one **821** of the patterned circuit layers **812** and **821**, such as a ground plane, bus, trace or line, to distribute a ground reference voltage Vss is realized from the concept of the coarse trace **82** shown in FIGS. **1**C and **2**C. The top one **812** of the patterned circuit layers **812** and **821**, such as a power plane, bus, trace or line, to distribute a power voltage Vcc is realized from the concept of the coarse trace **81** shown in FIGS. **1**C and **2**C. A polymer layer **98**, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, separates the patterned circuit layers **821** and **812**. Another polymer layer **99**, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, covers the top patterned circuit layer **812**. Alternatively, another polymer layer, such as benzocyclobutene (BCB), polyimide, parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, may be provided between the bottom-most patterned circuit layer **821** and the passivation layer **5**, described as the polymer layer **95** shown in FIG. **3**D. In FIGS. **1**C, **2**C and **3**C, the ground plane, trace or line **82** over the passivation layer **5**, used to distribute a ground reference voltage of Vss, is connected to the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** and the ground node Rs of the voltage regulator or converter circuit **41** through the openings **521**, **522**, **524** and **529** in the passivation layer **5** and the fine-line metal structures **621**, **622**, **624** and **629**, respectively. The power plane, trace or line **81** or **812** used to distribute a power voltage of Vcc is connected to the power nodes Tp, Up, Vp and Wp (not shown) of the internal circuits **21**, **22**, **23** and **24** and to the output nodes P of the voltage regulator or converter circuit **41** through the openings (not shown) in the polymer layer **98** and in the passivation layer **5** and through the fine-line metal structures **611**, **612**, **614** and **619'**, respectively, as illustrated in FIG. **3**B.

[0187] In FIG. **3**B, there is only one patterned circuit layer **811**, including a portion serving as the previously described thick and wide metal trace **81**P, power bus or plane delivering a power voltage input from an external circuit, over the passivation layer **5**, and another portion serving as the previously described thick and wide metal trace **81**, power bus or plane delivering a power voltage output from the voltage regulator or converter circuit **41**, over the passivation layer **5**. The patterned circuit layer **811** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8112** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8111**.

[0188] Referring to FIG. **3**B, regards to the process for forming the patterned circuit layer **811**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on a silicon-nitride layer of the passivation layer **5** and on contact pads **6490**, principally made of aluminum or copper, exposed by multiple openings **549**, **511**, **512** and **514** in the passivation layer **5**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper

layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8112** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8112** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8112** is removed using a wet-etching process or using a dry-etching process.

[0189] After the patterned circuit layer **811** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **811** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9949** may be formed in the polymer layer **99**, exposing a contact pad **8110** of the patterned circuit layer **811**.

[0190] Referring to FIG. **3**B, for forming a metal bump over the contact pad **8110**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8110** exposed by the opening **9919**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 0.5 and 10 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, and then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, having a thickness between 60 and 200 micrometers on the electroplated nickel layer in the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the metal bump can be reflowed to be shaped like a ball for a flip-chip assembly. The metal bump can be connected to a printed circuit board, ceramic substrate or another semiconductor chip.

[0191] Referring to FIG. **3**B, for forming another kind of metal bump over the contact pad **8110**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8110** exposed by the opening **9919**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a gold layer having a thickness between 6 and 25 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. The metal bump can be connected to a flexible substrate by a tape-automated bonding (TAB) process, or a glass substrate via anisotropic conductive film or paste (ACF or ACP).

[0192] Alternatively, referring to FIG. **3**B, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact pad **8110** exposed by the opening **9919**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9919** in the polymer layer **99**. Thereafter, a gold wire can be bonded onto the electroless plated gold layer in the opening **9919** in the polymer layer **99** using a wirebonding process.

[0193] Alternatively, referring to FIG. **3**B, a gold wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **811**, exposed by the openings **9919** in the polymer layer **99** using a wirebonding process.

[0194] Referring to FIG. **3**D, before the patterned circuit layer **811** is formed, a polymer layer **95** can be optionally formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads **6490**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9519**, **9519'**, **9511**, **9512** and **9514** may be formed in the polymer layer **95**, exposing multiple contact pads **6190** exposed by the openings **519**, **519'**, **511**, **512** and **514** in the passivation layer **5**. After the polymer layer **95** is formed, the patterned circuit layer **811** can be formed on the polymer layer **95** and on the contact pads **6190** exposed by the openings **519**, **519'**, **511**, **512** and **514**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer **95** and on the contact pads **6190** exposed by the openings **9519**, **9511**, **9512** and **9514** in the polymer layer **95**.

[0195] One of the patterned circuit layers **812** and **821** shown in FIG. **3**C, composing the thick metal traces or planes **81** and **82** over the passivation layer **5** may include an adhesion/barrier/seed layer **8111**, and a bulk conduction metal layer **8112**. The methods to form the patterned circuit layers **812** and **821** and the specification thereof may be based on the methods to form the patterned circuit layer **801**, **802** or **803** and the specification thereof shown in FIGS. **15**A-**15**L, **16**A-**16**M, **17**A-**17**J, **18**A-**18**I and **19**A-**19**I.

[0196] In FIG. **3**C, the thick and wide metal trace, bus or plane **82**, used to deliver a ground voltage, may have a lower patterned circuit layer under an upper patterned circuit layer of the thick and wide metal trace, bus or plane **81**, used to deliver a power voltage Vcc output from the voltage regulator or converter circuit **41**. Alternatively, the thick and wide metal trace, bus or plane **82**, used to deliver a ground voltage, may have an upper patterned circuit layer over a lower patterned circuit layer of the thick and wide metal trace, bus or plane **81**, used to deliver a power voltage Vcc output from the voltage regulator or converter circuit **41**. A polymer layer having a thickness between 2 and 30 micrometers may be between the upper and lower patterned circuit layers. Each of the lower and upper patterned circuit layers may have an electroplated copper layer having a thickness between 2 and 30 micrometers.

[0197] Referring to FIG. **3**C, there may be multiple patterned circuit layers **821** and **812**, including the previously described ground bus or plane **82** and the previously described power bus or plane **81**, used to deliver a power voltage output from the voltage regulator or converter circuit **41**, over the ground bus or plane **82**, over the passivation layer **5**. The process for forming the patterned circuit layer **821** on the passivation layer **5** and on the contact pads **6290** exposed by the openings **529**, **521**, **522** and **524** can be referred to as the process for forming the patterned circuit layer **811** shown in FIG. **3**B on the passivation layer **5** and on the contact pads **6190** exposed by the openings **519**, **511**, **512** and **514**. The patterned circuit layer **821** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8212** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8211**. The patterned circuit layer **812** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8122** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8121**.

[0198] Referring to FIG. **3**C, after the patterned circuit layer **821** is formed, a polymer layer **98** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **821** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9829** may be formed in the polymer layer **98**, exposing a contact pad of the patterned circuit layer **821**.

[0199] Referring to FIG. **3**C, regards to the process for forming the patterned circuit layer **812**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **98** and on the contact pad of the patterned circuit layer **821** exposed by the opening **9829** in the polymer layer **98**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8122** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8122** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8122** is removed using a wet-etching process or using a dry-etching process.

[0200] After the patterned circuit layer **812** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **812** and on the polymer layer **98**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9929** may be formed in the polymer layer **99**, exposing a contact pad **8120** of the patterned circuit layer **812**.

[0201] Referring to FIG. **3**C, for forming a metal bump over the contact pad **8120**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8120** exposed by the opening **9929**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 0.5 and 10 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, and then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, having a thickness between 60 and 200 micrometers on the electroplated nickel layer in the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the metal bump can be reflowed to be shaped like a ball. The metal bump can be connected to a printed circuit board, ceramic substrate or another semiconductor chip.

[0202] Referring to FIG. **3**C, for forming another kind of metal bump over the contact pad **8120**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8120** exposed by the opening **9929**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a gold layer having a thickness between 6 and 25 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. The metal bump can be connected to a flexible substrate by a tape-automated bonding (TAB) process, or a glass substrate via anisotropic conductive film or paste (ACF or ACP).

[0203] Alternatively, referring to FIG. **3**C, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact pad **8120** exposed by the opening **9929** in layer polymer layer **99**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9929** in the polymer layer **99**. Thereafter, a gold wire can be bonded onto the electroless plated gold layer in the opening **9929** in the polymer layer **99** using a wirebonding process.

[0204] Alternatively, referring to FIG. **3**C, a gold wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **812**, exposed by the openings **9929** in the polymer layer **99** using a wirebonding process.

[0205] Alternatively, before the patterned circuit layer **821** is formed, a polymer layer can be optionally formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads **6290**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings may be formed in the polymer layer, exposing multiple contact pads **6290** exposed by the openings **529**, **521**, **522** and **524** in the passivation layer **5**. After the polymer layer is formed, the patterned circuit layer **821** can be formed on the polymer layer and on the contact pads **6290** exposed by the openings **529**, **521**, **522** and **524**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer and on the contact pads **6290** exposed by the openings in the polymer layer.

[0206] In some applications, some metal lines, traces or planes used to transmit a digital signal or analog signal can be provided on the polymer layer **98** and at the same level as the power traces, buses or planes **812**. Alternatively, some metal lines, traces or planes used to transmit a digital signal or analog signal can be provided on the passivation layer **5** and at the same level as the ground traces, buses or planes **82**. There are more other structures formed over the passivation layer **5**, described as below: (1) in the first application for high performance circuits or high precision analog circuits, another patterned circuit layer, such as signal planes, buses, traces or lines, used to transmit a digital signal or an analog signal (not shown) may be added between the power lines, buses or planes **812** and the ground lines, buses or planes **821**. Polymer layers, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer

or silicone, (not shown) over and under the signal planes, buses, traces or lines are provided to separate the signal planes, buses, traces or lines from the power traces, buses or planes **812** and to separate the signal planes, buses, traces or lines from the ground traces, buses or planes **821**, respectively; (2) in the second application of the high current or the high precision circuit, another patterned circuit layer, such as ground planes, buses, traces or lines, (not shown) used to distribute a ground reference voltage may be added over the power traces, buses or planes **812**. The power traces, buses or planes **812** are sandwiched by the ground traces, buses or planes **821** under the power traces, buses or planes **812** and the newly-added ground traces, buses or planes over the power traces, buses or planes **812**, therefore, forming a Vss/Vcc/Vss structure (the stack is from the bottom to the top) over the passivation layer **5**. A polymer layer, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, is provided between the newly-added ground planes, buses, traces or lines and the power traces, buses or planes **812**. A cap polymer layer, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, covers the newly-added ground planes, buses, traces or lines; (3) in the third application of the high current or the high precision circuit, if required, based on the second application of the Vss/Vcc/Vss structure, another patterned circuit layer, such as power planes, buses, traces or lines, (not shown) used to distribute a power voltage can be further formed over the top ground planes, buses, traces or lines (not shown) over the power traces, buses or planes **812**, creating a Vss/Vcc/Vss,/Vcc structure, (the stack is from the bottom to the top) over the passivation layer **5**. A polymer layer, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, is provided between the newly-added power planes, buses, traces or lines and the top ground traces, buses or planes **81**. A cap polymer layer, such as polyimide, benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, having a thickness of between 2 and 30 microns, covers the newly-added power planes, buses, traces or lines. The previously described structures provide a robust power supply for high current circuits, high precision analog circuits, high speed circuits, low power circuits, power management circuits, and high performance circuits.

[0207] FIG. **4** shows a circuit design for the voltage regulator or converter circuit **41** in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D. This circuit design is for a voltage regulator or converter circuit **41** usually used in the modern DRAM design as described in "Semiconductor Memories: A handbook of Design, Manufacture and Application" Second Edition, By B. Prince, published by John Wiley & Sons, 1991. The voltage regulator or converter circuit **41** shown in FIG. **4** provides both voltage regulating function and voltage converting function. The external voltage Vdd can be converted to an output voltage Vcc varying at a desired voltage level Vcc**0**, and the ratio of the difference of between Vcc and Vcc**0** to Vcc**0** is less than 10%, and preferably less than 5%. As discussed in the section of "description of related arts", more modern IC chips require on-chip voltage converters to convert the external (system, board, module, or card level) power supply voltage to a voltage level required by the chip. Moreover, some chips, such as a DRAM chip, even require dual or even triple voltage levels on the same chip: for example, 3.3 V for peripheral control circuits, while 1.5 V for the memory cells in the cell array area.

[0208] The voltage regulator or converter circuit **41** in FIG. **4** includes two circuit blocks: a voltage reference generator **410** and a current mirror circuit **410'**. The voltage reference generator **410** generates a reference voltage V_R at the node R, insensitive to the voltage fluctuation of the external power supply voltage Vdd at node **4199**. Vdd is also the input supply voltage of the reference voltage generator **410**. The voltage reference generator **410** includes two paths of voltage divider. One path includes three p-channel MOS transistors, **4101**, **4103** and **4105** connected in series, and the other path includes two p-channel MOS transistors **4102** and **4104** connected in series. With the drain of the MOS transistor **4103** coupled to the gate of the MOS transistor **4104**, the output reference voltage V_R is regulated. When Vdd is fluctuated with a rise, the voltage level at node G will rise, resulting in a weaker turn-on of the MOS transistor **4104**. When the MOS transistor **4104** is turned-on weaker, V_R drops or rises with a smaller extent. Similarly, V_R rises or drops with a smaller extent, when Vdd is fluctuated with a drop. This explains the voltage regulation behavior of the voltage reference generator **410**. The output of the voltage reference generator **410** is used as a reference voltage of the current mirror circuit **410'**. The current mirror circuit **410'** provides a power supply with voltage at a desired constant level and with large current capability for an IC chip. The current mirror circuit **410'** also eliminates possible huge power consumption or waste by avoiding a direct high current path from Vdd to Vss in the paths of voltage dividers. With the drain of the p-channel MOS transistor **4109** coupled to the gate of the output p-channel MOS transistor **4106**, and with the output voltage node P coupled to the gate of the reference-voltage-mirror p-channel MOS transistor **4110**, the output voltage Vcc is regulated, and accordingly the output voltage level Vcc can be designed at a desired level. The conductance transistor **4112** is a small p-channel MOS transistor with a gate connected to Vss, hence the transistor **4112** is always turned on. The conductance transistor **4111** is a large p-channel MOS, and its gate is controlled by a signal ϕ. The transistor **4111** is turned on when the internal circuits or internal circuit units are in an active cycle, resulting in a fast response of the current path provided by the p-channel MOS transistor **4109** and n-channel MOS transistor **4107**, and of the current path provided by the p-channel MOS transistor **4110** and n-channel MOS transistor **4108**. The turn-on of the transistor **4111** minimizes the output supply Vcc bounce caused by a large transient current demanded by the internal circuits, such as **21**, **22**, **23** and **24**, shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D. When the internal circuits or internal circuit units are in idle cycle, the transistor **4111** is turned off to save power consumption.

Second Embodiment: Over-passivation Interconnection for Internal Circuits

[0209] The coarse traces over the passivation layer **5** described in the first embodiment can be alternatively used as an interconnection of IC internal circuits to transmit a signal from an internal circuit to another one or other ones. In this application, the coarse metal conductor over a passivation layer is used to transmit a signal or data from an output node Xo of an internal circuit **21** to input nodes Ui, Vi and Wi of other internal circuits **22**, **23** and **24**, as shown in FIG. **5**B.

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When designed as a bundle of metal lines or metal traces that connects a set of similar nodes for inputting or outputting data signals, bit signals or address signals, for example, between two internal functional circuits separated in a longer distance (for example, in the distance of 1 mm or more 500 microns), such as the 8-, 16-, 32-, 64-, 128-, 256-, 512-, or 1024-bits of data (or address) connection between a processor unit and a memory unit on the same chip, the lines or traces are often referred to as buses, such as word buses or bit buses used in a memory. For these applications, the disclosure provides a thick metal trace, bus or plane **83** over a passivation layer **5**, far away from underlying MOS devices, to connect multiple internal circuits **21**, **22**, **23** and **24**, as shown in FIG. **5**B, and accordingly allows the electrical signal to pass over MOS devices without perturbing the underlying MOS devices and without significant degradation of signal integrity. It is noted that the thick metal trace, bus or plane **83** over the passivation layer **5** connects the nodes of the internal circuits **21**, **22**, **23** and **24** not through any off-chip input/output circuit connected with an external circuit, and is not connected up to an external circuit. As the previously described thick metal trace, bus or plane **83** over the passivation layer **5** may induce only very low parasitic capacitance, the signal passing through the thick metal trace, bus or plane **83** will not be dramatically degraded. It makes this disclosure very suitable for high-speed, low power, high current or low voltage applications. In most cases of this disclosure, no additional amplifier, driver/receiver or repeater is required to help sustain the integrity of the signal passing through the thick metal trace, bus or plane **83**. In some cases of this disclosure, an internal driver, internal receiver, internal tri-state buffer, or repeater, including MOS transistors with a smaller size as compared to those of the off-chip circuits connected with an external circuit, is required to transmit a signal passing through a long path, such as the thick metal trace, bus or plane **83** having a length of larger than 500 microns or larger than 1000 microns.

[0210] FIGS. **5**B, **6**B, and **7**B show a second exemplary embodiment of the disclosure. FIG. **5**B shows a simplified circuit diagram where a metal trace, bus or plane **83** over the passivation layer **5** connects multiple internal circuits **21**, **22**, **23** and **24** to transmit a signal from an output node Xo of an internal circuit **21** to input nodes Ui, Vi and Wi of the internal circuits **22**, **23** and **24**. FIG. **6**B shows a top view of the semiconductor chip realizing the circuitry shown in FIG. **5**B. FIG. **7**B shows a cross-sectional view of the semiconductor chips realizing the circuitry shown in FIGS. **5**B. FIG. **6**B shows a top view of the semiconductor chip shown in FIG. **7**B, and the patterned circuit layer **831**, such as signal plane, bus, trace or line, to transmit a signal from the internal circuit **21** to the internal circuits **22**, **23** and **24** is realized from the concept of the coarse trace **83** shown in FIGS. **5**B and **6**B. The coarse trace **83** shown in FIGS. **5**B and **6**B indicates a trace of an over-passivation scheme **102** formed over the passivation layer **5**, and the fine traces **631**, **632** (including **632***a*, **632***b* and **632***c*) and **634** shown in FIG. **5**B and the fine traces **632***a*, **632***b* and **632***c* shown in FIGS. **6**B indicate traces formed under the passivation layer **5**.

[0211] As shown in FIGS. **5**B, **6**B and **7**B, the internal circuit **21** includes an input node Xi to receive a signal and an output node Xo to output an electrical signal to the internal circuits **22**, **23** and **24**. The internal circuit **21** can be a logic gate, such as inverter, NOR gate, NAND gate, OR gate, AND gate, or an internal buffer (an inverter, an internal driver, or an internal tri-state buffer, shown in FIGS. **5**C, **5**D, and **5**E, respectively). Through the coarse metal scheme **83** over the passivation layer **5**, the input nodes Ui, Vi and Wi of the internal logic circuits **22**, **23** and **24** (two NOR gates **22** and **24**, and one NAND gate **23**) are able to receive data or signal sent from the internal circuit **21**. The voltage level at input nodes Ui, Vi and Wi are between Vdd and V_{ss} with very minimal degradation and noise in that the interconnecting metal trace or bus **83** over the passivation layer **5** has low resistance and create low capacitance. It is noted that in this design the thick metal trace or bus **83** is not connected to off-chip circuits connected to an external circuit, such as ESD circuit, off-chip driver, off-chip receiver, or off-chip tri-state buffer circuit, resulting in speed improvement and power consumption reduction.

[0212] FIGS. **5**A, **6**A and **7**A illustrate the connection between the internal circuits **21**, **22**, **23** and **24**. The technique illustrated in FIGS. **5**A, **6**A and **7**A relies on the fine-line metal traces **6311**, **6321**, **6341** and **638** under the passivation layer **5** to pass data output from the internal circuit **21** to the internal circuits **22**, **23** and **24**, without relying on any patterned circuit layer over the passivation layer **5**.

[0213] FIGS. **5**B and **6**B reveal that the coarse metal scheme **83** is built over the passivation layer **5** of the IC chip, and is connected to the internal circuits **21**, **22**, **23** and **24**. FIGS. **5**A, **6**A and **7**A show that the internal circuit **21** is connected to a NOR gate **22** through segments **6311**, **638**, **6321***a* and **6321***b* of the fine-line metal structures under the passivation layer **5**, to a NAND gate **23** through segments **6311**, **638**, **6321***a* and **6321***c* of the fine-line metal structures under the passivation layer **5**, and to another NOR gate **24** through segments **6311**, **638** and **6341** of the fine-line metal structures under the passivation layer **5**. In the present disclosure, the second segment **638** of the fine-line metal structure is replaced by a coarse metal conductor **83** over the passivation layer **5**, as shown in FIGS. **5**B and **6**B. A signal output from an output node (usually the drain of a MOS transistor in the internal circuit **21**) of the internal circuit **21** may pass through a segment **631** of the fine-line metal structure under the passivation layer **5**, then through an opening **531** in the passivation layer **5**, then through the interconnection scheme **83** over the passivation layer **5**, then through an opening **534** in the passivation layer **5**, then through a segment **634** of the fine-line metal structure under the passivation layer **5**, and then to an input node (usually the gate of an MOS transistor in the NOR gate **24**) of the NOR gate **24**. A signal output from an output node (usually the drain of an MOS transistor in the internal circuit **21**) of the internal circuit **21** may pass through a segment **631** of the fine-line metal structure under the passivation layer **5**, then through the opening **531** in the passivation layer **5**, then through the interconnection scheme **83** over the passivation layer **5**, then through an opening **532** in the passivation layer **5**, then through a segment **632***a* and a segment **632***b* or **632***c* of the fine-line metal interconnection scheme under the passivation layer **5**, and then to the input nodes (usually the gates of MOS transistors in the NOR gate **22** and the NAND gate **23**, respectively) of a NOR gate **22** and a NAND gate **23**.

[0214] Alternatively, when the internal circuit **21** is a NOR gate, the internal circuits **22**, **23** and **24** may be NOR gates, OR gates, NAND gate or AND gates. When the internal circuit **21** is an OR gate, the internal circuits **22**, **23** and **24** may be NOR gates, OR gates, NAND gate or AND gates. When the internal circuit **21** is a NAND gate, the internal circuits **22**, **23** and **24** may be NOR gates, OR gates, NAND

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gate or AND gates. When the internal circuit **21** is a AND gate, the internal circuits **22**, **23** and **24** may be NOR gates, OR gates, NAND gate or AND gates. When a NMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2, a NMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10 or preferably ranging from, e.g., about 0.2 to 2. When a NMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2, a PMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. When a PMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4, a NMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2. When a PMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4, a PMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. In the previously described case, a signal output from the output node Xo of the internal circuit **21** may pass through the thick metal plane, bus, trace or line **83** to the internal circuits **22**, **23** and **24**, with a current, passing through the thick metal plane, bus, trace or line **83**, ranging from, e.g., about 50 microamperes to 2 milliamperes, and preferably ranging from, e.g., about 100 microamperes to 1 milliampere. The fine line metal structures **634**, **632** and **631** shown in **7**B, **7**C and **7**D may be formed with multiple circuit layers **60** and multiple stacked plugs **60'**, upper plugs **60'** being aligned with bottom plugs **60'**. When the circuit layers **60** are formed with electroplated copper, the stacked plugs **60'** may be formed with electroplated copper. When the circuit layers **60** are formed with sputtered aluminum, the stacked plugs **60'** may be formed with chemical vapor deposited tungsten. There are multiple insulating layers **30** under the passivation layer **5**, and each one is positioned between the neighboring two of the circuit layers **60**. The insulating layers **30** made of one or more inorganic materials may include a layer of silicon oxide with a thickness of between 0.01 and 2 micrometers, may include a layer of fluorine doped silicate glass (FSG) with a thickness of between 0.01 and 2 micrometers, or may include a layer with a lower dielectric constant, such as between 1.5 and 3.5, having a thickness of between 0.01 and 2 micrometers, such as black diamond film or a material containing hydrogen, carbon, oxygen and silicon.

[0215] The thick metal trace or plane **83** over the passivation layer **5**, shown in FIG. **5**B and **6**B, may be composed of only one patterned circuit layer **831**, as shown in FIG. **7**B, or multiple patterned circuit layers **831** and **832**, as shown in FIG. **7**C. In FIG. **7**B, the patterned circuit layer **831**, such as a signal plane, bus, trace or line, to transmit a signal is realized from the concept of the coarse trace **83** shown in FIGS. **5**B and **6**B. In FIG. **7**C, the patterned circuit layers **831** and **832**, such as signal planes, buses, traces or lines, to transmit a signal is realized from the concept of the coarse trace **83** shown in FIGS. **5**B and **6**B. When the thick metal traces or plane **83** over the passivation layer **5**, shown in FIGS. **5**B and **6**B, is composed of multiple patterned circuit layers **831** and **832**, as shown in FIG. **7**C, a polymer layer **98**, such as polyimide (PI), benzocyclobutene (BCB), parylene, photoepoxy SU-8, epoxy-based material, elastomer or silicone, may be between the neighboring patterned circuit layers **831** and **832**, separating the patterned circuit layers **831** and **832**. The polymer layer **98** may have a thickness between 2 and 30 micrometers. A polymer layer **99**, such as polyimide (PI), benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, may be on the topmost one **832** of the patterned circuit layers **831** and **832**, separated by the above mentioned polymer layers **98**, over the passivation layer **5**, as shown in FIG. **7**C, or on the only one patterned circuit layer **831**, as shown in FIGS. **7**B and **7**D. The polymer layer **99** may have a thickness between 2 and 30 micrometers. It is noted that no opening in the polymer layer **99** exposes the patterned circuit layer **831** or **832**, and the patterned circuit layer **831** or **832** has no pad connected up to an external circuit, as shown in FIGS. **7**B, **7**C and **7**D. Alternatively, a polymer layer **95**, such as polyimide (PI), benzocyclobutene (BCB), parylene, epoxy-based material, photoepoxy SU-8, elastomer or silicone, may be between the passivation layer **5** and the bottommost one **831** of the patterned circuit layers **831** and **832**, separated by the above mentioned polymer layers **98**, for the structure shown in FIG. **7**C, or between the passivation layer **5** and the only one patterned circuit layer **831**, as shown in FIG. **7**D. The polymer layer **95** may have a thickness between 2 and 30 micrometers. Multiple openings **9519**, **9519'**, **9511**, **9512** and **9514** in the polymer layer **95** are substantially aligned with the openings **519**, **519'**, **511**, **512** and **514** in the passivation layer **5**, respectively. The openings **9531**, **9532** and **9534** in the polymer layer **95** expose the pads exposed by the openings **531**, **532** and **534** in the passivation layer **5**, respectively.

[0216] The openings **9531**, **9532** and **9534** in the polymer layer **95** have lower portions having widths or transverse dimensions larger than those of the openings **531**, **532** and **534** in the passivation layer **5** aligned with the openings **9531**, **9532** and **9534**, respectively. The openings **9531**, **9532** and **9534** in the polymer layer **95** further expose the passivation layer **5** close to the openings **531**, **532** and **534**. The shape of the openings **531**, **532** and **534** from a top perspective view may be round, square, rectangular or polygon. If the openings **531**, **532** and **534** are round, the openings **531**, **532** and **534**

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may have a diameter of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **531**, **532** and **534** are square, the openings **531**, **532** and **534** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **531**, **532** and **534** are rectangular, the openings **531**, **532** and **534** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns, and a length of between 1 micron and 1 centimeter. If the openings **531**, **532** and **534** are polygon having more than five sides, the openings **531**, **532** and **534** have a largest diagonal length of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. Alternatively, the openings **531**, **532** and **534** have a largest transverse dimension of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. In a case, the openings **531**, **532** and **534** have a width of between 0.1 and 30 microns, with the lower portion of the openings **9531**, **9532** and **9514** in the polymer layer **95** having a width of between 20 and 100 microns.

[0217] Each of the patterned circuit layers **831** and **832** composing the thick metal trace or plane **83** over the passivation layer **5**, shown in FIGS. **7**B, **7**C and **7**D, may include an adhesion/barrier/seed layer **8311**, **8311***a*, **8311***b* or **8321** and a bulk conduction metal layer **8112**, **8312***a*, **8312***b* or **8322**. The methods to form the patterned circuit layer **831** or **832** and the specification thereof may follow the methods to form the patterned circuit layer **801**, **802** or **803** and the specification thereof shown in FIGS. **15**A-**15**L, **16**A-**16**M, **17**A-**17**J, **18**A-**18**I and **19**A-**19**I.

[0218] In FIGS. **7**B and **7**D, there is only one patterned circuit layer **831**, including a portion serving as the previously described thick and wide metal trace **83** over the passivation layer **5**. The patterned circuit layer **831** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8312** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8311**.

[0219] Referring to FIG. **7**B, regards to the process for forming the patterned circuit layer **831**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on a silicon-nitride layer of the passivation layer **5** and on contact pads **6390**, principally made of aluminum or copper, exposed by multiple openings **531**, **532** and **534** in the passivation layer **5**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8312** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8312** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8312** is removed using a wet-etching process or using a dry-etching process.

[0220] After the patterned circuit layer **831** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **831** and on the nitride layer of the passivation layer **5** and then curing the spin-on coated polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. No opening is formed in the polymer layer **99** to expose the thick and wide metal trace **83**.

[0221] Referring to FIG. **7**D, before the patterned circuit layer **831** is formed, a polymer layer **95** can be optionally formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads exposed by the openings **531**, **532** and **534** in the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9531**, **9532** and **9534** may be formed in the polymer layer **95**, exposing multiple contact pads exposed by the openings **531**, **532** and **533** in the passivation layer **5**. After the polymer layer **95** is formed, the patterned circuit layer **831** can be formed on the polymer layer **95** and on the contact pads exposed by the openings **531**, **532** and **533**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer **95** and on the contact pads exposed by the openings **9531**, **9532** and **9534** in the polymer layer **95**.

[0222] Alternatively, referring to FIG. **7**C, there may be multiple patterned circuit layers **831** and **832**, including a portion serving as the previously described thick and wide metal trace **83**, over the passivation layer **5**. The process for forming the patterned circuit layer **831** shown in FIG. **7**C can be referred to as the process for forming the patterned circuit layer **831** shown in FIG. **10**B. The patterned circuit layer **832** may contain an adhesion/barrier layer, a seed layer on the

adhesion/barrier layer, and an electroplated metal layer **8322** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8321**.

[0223] Referring to FIG. **7**C, after the patterned circuit layer **831** is formed, a polymer layer **98** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **831** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between **30** and **240** minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9831** and **9834** may be formed in the polymer layer **98**, exposing multiple contact pads of the patterned circuit layer **831**.

[0224] Referring to FIG. **7**C, regards to the process for forming the patterned circuit layer **832**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **98** and on the contact pads of the patterned circuit layer **831** exposed by multiple openings **9831** and **9834** in the polymer layer **98**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8322** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8322** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8322** is removed using a wet-etching process or using a dry-etching process.

[0225] After the patterned circuit layer **832** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **832** and on the polymer layer **98**, and then curing the spin-on coated polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient.

[0226] Alternatively, referring to FIG. **7**C, before the patterned circuit layer **831** is formed, a polymer layer **95** as mentioned in FIG. **7**D can be optionally formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads exposed by the openings **531**, **532** and **534** in the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9531**, **9532** and **9534** may be formed in the polymer layer **95** as mentioned in FIG. **7**D, exposing multiple contact pads exposed by the openings **531**, **532** and **533** in the passivation layer **5**. After the polymer layer **95** is formed, the patterned circuit layer **831** can be formed on the polymer layer **95** and on the contact pads exposed by the openings **531**, **532** and **533**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer **95** and on the contact pads exposed by the openings **9531**, **9532** and **9534** in the polymer layer **95**.

[0227] FIG. **7**C is similar to FIG. **7**B except the thick metal planes, buses or traces **83** are composed of two patterned circuit layers **831** and **832**; the bottom one is composed of segments **831** a and **831** b. A polymer layer **98** separates the patterned circuit layer **831** from the patterned circuit layer **832**. In FIG. **7**C, the thick metal plane, trace or bus **831** in FIG. **7**B is replaced by the thick metal plane, trace or bus **831***a*, **831***b* and **832**. Referring to FIG. **7**C, a signal output from the output node (usually the drain of an MOS transistor in the internal circuit **21**) of the internal circuit **21** passes through the fine-line metal buses or traces **631** under the passivation layer **5**, then through the opening **531** in the passivation layer **5**, then through the metal trace or bus **831***b* over the passivation layer **5**, (1) in a first path, then up through an opening **9831** in the polymer layer **98**, then through the metal bus or trace **832** on the polymer layer **98**, then down through an opening **9834** in the polymer layer **98**, then through the metal trace or bus **831***a* over the passivation layer **831***a*, then through an opening **534** in the passivation layer **5**, then through the fine-line metal structure **634** under the passivation layer **5**, and to the input node (usually the gate of an MOS transistor in the NOR gate **24**) of the NOR gate **24**; (2) in a second path, then down through an opening **532** in the passivation layer **5**, then through the fine-line metal interconnection scheme **632** under the passivation layer **5**, and then to the input nodes (usually the gates of MOS transistors in the NOR gate **24** and the NAND gate **23**, respectively) of the NOR gate **22** and the NAND gate **23**.

[0228] Referring to **5**B, **6**B, **7**B, **7**C and **7**D, the metal trace or bus **83** over the passivation layer **5** can be connected to an off-chip I/O circuit connected to an external circuit, and

accordingly the thick metal trace or bus **83** has no significant voltage drop or signal degradation. The over-passivation scheme **102** shown in FIG. **7**B includes the polymer layer **99** and the metal trace **83** provided by the patterned circuit layer **831**. The over-passivation scheme **102** shown in FIG. **7**C includes two polymer layers **98** and **99** and the metal trace **83** provided by the patterned circuit layers **831** and **832**, and the openings **9831** and **9834** in the polymer layer **98** are over the patterned circuit layers **831**. The over-passivation scheme **102** shown in FIG. **7**D includes two polymer layers **95** and **99** and the metal trace **83** provided by the patterned circuit layer **831**, and the openings **9531**, **9532** and **9534** are in the polymer layer **95**.

[0229] Now refer to FIGS. **5**C-**5**E showing internal buffer circuits applied to the internal circuit **21**. The internal circuit **21** shown in FIG. **5**B, **6**B, **7**B, **7**C and **7**D may be an internal inverter shown in FIG. **5**C. In a first application, the size of the n-channel MOS **2101** and p-channel MOS **2102** can be designed in a size often employed in the internal circuits **22**, **23** and **24**. The size of an MOS transistor is defined as a ratio of a physical channel width thereof to a physical channel length thereof. The n-channel MOS transistor **2101** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to **10**, or preferably ranging from, e.g., about 0.2 to 2. The p-channel MOS transistor **2102** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. In the first application, a current passing through the thick metal trace **83** over the passivation layer **5** and outputting from the node Xo of the internal circuit **21** may be in a range of between 50 μA and 2 mA, and preferably of between 100 μA and 1 mA. In a second application, a larger drive current is required for the output of the inverter **211**, for example, when a heavy load is demanded by the load internal circuits **22**, **23** and **24**, or when the internal circuits **22**, **23** and **24** are located far away from the internal circuit **21**, requiring interconnection metal lines or traces connecting the internal circuit **21** and the internal circuits **22**, **23** and **24** in a distance of larger than 1 mm or of larger than 3 mm, for example. In the second application, the current output from the inverter **211** is higher than that output from the regular internal circuit, and is, for example, at 1 mA or 5 mA, or in a range of between 500 μA and 10 mA, and preferably of between 700 μA and 2 mA. Hence, in the second application, the n-channel MOS transistor **2101** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 1.5 to 30, and preferably ranging from, e.g., about 2.5 to 10. The p-channel MOS transistor **2102** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 3 to 60, and preferably ranging from, e.g., about 5 to 20.

[0230] When the inverter **211** shown in FIG. **5**C is applied to the internal circuit **21** as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, the drains of the n-channel MOS transistor **2101** and p-channel MOS transistor **2102**, serving as the output node Xo of the internal circuit **21**, are connected to the thick metal traces or buses **83**, **831** or **832** over the passivation layer **5** as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D. The gates of the n-channel MOS transistor **2101** and p-channel MOS transistor **2102** serve as the input node Xi of the internal circuit **21**.

[0231] Referring to FIG. **5**C, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** may connect the node P of the voltage regulator or converter circuit **41** and the source of the p-channel MOS device **2102**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** may connect the node Rs of the voltage regulator or converter circuit **41** and the source of the n-channel MOS device **2101**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0232] FIGS. **5**D and **5**E show an internal driver **212** and internal tri-state output buffer **213**, respectively. When the internal driver **212** shown in FIG. **5**D is applied to the internal circuit **21** as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, the drains of a n-channel MOS transistor **2103** and p-channel MOS transistor **2104**, serving as the output node Xo of the internal circuit **21**, are connected to the thick metal traces or buses **83**, **831** or **832** over the passivation layer **5**. The gates of a n-channel MOS transistor **2103'** and p-channel MOS transistor **2104'** serve as the input node Xi of the internal circuit **21**. The drains of the n-channel MOS transistor **2103'** and p-channel MOS transistor **2104'** are connected to the gates of the n-channel MOS transistor **2103** and p-channel MOS transistor **2104**.

[0233] When the internal tri-state output buffer **213** shown in FIG. **5**E is applied to the internal circuit **21** as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, the drains of a n-channel MOS transistor **2107'** and p-channel MOS transistor **2108'** with a switch function controlled by an Enable signal transmitted to the gate of the n-channel MOS transistor **2107'** and Enable (bar) signal transmitted to the gate of the p-channel MOS transistor **2108'**, serving as the output node Xo of the internal circuit **21**, are connected to the thick metal traces or buses **83**, **831** or **832** over the passivation layer **5** as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D. The gates of a n-channel MOS transistor **2107** and p-channel MOS transistor **2108** serve as the input node Xi of the internal circuit **21**. The drains of a n-channel MOS transistor **2107** and p-channel MOS transistor **2108** are connected to the sources of the n-channel MOS transistor **2107'** and p-channel MOS transistor **2108'**, respectively.

[0234] The internal driver **212** or internal tri-state output buffer **213**, used to drive a signal through the post-passivation metal traces **83** and to the internal circuits **22**, **23** and **24**, as shown in FIG. **5**D or **5**E, is similar to the off-chip driver or off-chip tri-state output buffer used to drive an external circuitry, to be discussed in the following FIG. **11**A or **11**D, respectively, except that (1) the output node Xo of the internal driver **212** or internal tri-state output buffer **213** is not connected to an external circuit; (2) the largest one of p-MOS transistors in the internal driver **212** or internal tri-state output

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buffer **213** has a ratio of a physical channel width thereof to a physical channel length thereof smaller than that of the largest one of p-MOS transistors in the off-chip driver or off-chip tri-state output buffer connected to an external circuit. The internal tri-state output buffer **213** provides drive capability and switch capability, and is particularly useful to transmit a data signal or an address signal in a memory chip through the thick metal lines or traces **83** over the passivation layer **5** acting as data or address buses.

[0235] In FIG. **5**B, a relatively large drive current may be required at the output node Xo of the internal circuit **21** when a heavy load is demanded by the internal circuits **22**, **23** and **24**, or when the internal circuits **22**, **23** and **24** are far away from the internal circuit **21** in a distance of larger than **1** mm or of larger than **3**mm. To provide a relatively large drive current, the internal circuit **21** can be designed as an internal driver **212** shown in FIG. **5**D or an internal tri-state output buffer **213** shown in FIG. **5**E.

[0236] In FIGS. **5**D and **5**E, the n-channel MOS transistors **2103**, **2107** and **2107'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 1.5 to 30, and preferably ranging from, e.g., about 2.5 to 10. The p-channel MOS transistors **2104**, **2108** and **2108'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 3 to 60, and preferably ranging from, e.g., about 5 to 20. In FIG. **5**D, the n-channel MOS transistor **2103'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2, and the p-channel MOS transistor **2104'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. Referring to FIGS. **5**B, **5**D and **5**E, the internal driver **212** or internal tri-state buffer **213** may drive a signal output from the output node Xo thereof through the thick metal trace or bus **83** over the passivation layer **5** to the input nodes Ui, Vi and Wi of the internal circuits **22**, **23** and **24** but not to an external circuit. A current passing through the thick metal trace or line **83** over the passivation layer **5** and outputting from the node Xo of the internal circuit **21**, provided by the internal driver **212** or internal tri-state buffer **213**, may be between 500 μA and 10 mA, and preferably between 700 μA and 2 mA.

[0237] Referring to FIG. **5**D, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** and the sources of the p-channel MOS devices **2104** and **2104'**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the sources of the n-channel MOS devices **2103** and **2103'**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0238] Referring to FIG. **5**E, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** and the source of the p-channel MOS device **2108**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the source of the n-channel MOS device **2107**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0239] Alternatively, when a NMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 1.5 to 30, and preferably ranging from, e.g., about 2.5 to 10, a NMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of physical channel width to physical channel length ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2. When a NMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 1.5 to 30, and preferably ranging from, e.g., about 2.5 to 10, a PMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. When a PMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 3 to 60, and preferably ranging from, e.g., about 5 to 20, a NMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2. When a PMOS transistor in the internal circuit **21** having a drain as the output node Xo of the internal circuit **21** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 3 to 60, and preferably ranging from, e.g., about 5 to 20, a PMOS transistor in the internal circuit **22**, **23** or **24** having a gate as the input node

Ui, Vi and Wi of the internal circuit **22**, **23** or **24** has a ratio of a physical channel width to a physical channel length ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. In the previously described case, a signal output from the output node Xo of the internal circuit **21** may pass through the thick metal plane, bus, trace or line **83** to the internal circuits **22**, **23** and **24**, with a current, passing through the thick metal plane, bus, trace or line **83**, ranging from, e.g., about 500 microamperes to 10 milliamperes, and preferably ranging from, e.g., about 700 microamperes to 2 milliamperes.

[0240] The concept shown in FIG. **5**B can be applied to a memory chip, as illustrated in FIGS. **5**F-**5**J.

[0241] Referring to FIG. **5**F, the previously described tri-state output buffer **213** is employed to be the internal circuit **21** shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D and has an input node Xi connected to an output node of an amplifier **214** and an output node Xo connected to the internal circuits **22**, **23** and **24**, such as logic gates, through the above mentioned thick metal plane, bus or trace **83**, **831** or **832** over the passivation layer **5**, as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, and the internal circuits **22**, **23** and **24** may alternatively be NOR gate, NAND gate, AND gate, OR gate, operational amplifier, adder, multiplexer, diplexer, multiplier, A/D converter, D/A converter, CMOS transistor, bipolar CMOS transistor or bipolar circuit. The semiconductor chip may include a memory array including multiple memory cells connected to word lines, bit lines and bit (bar) lines. Each pair of bit line, such as **2171**, and bit (bar) line, such as **2172**, is connected to one of the amplifiers, such as **214**, through the channel of the n-channel MOS transistors **2123** and **2122** controlled by CS**1** node. When the n-channel MOS transistors **2122** and **2123** are turned off in an inactive cycle, the noise on the bit line **2171** or on the bit (bar) line **2172** can not be transmitted to the sense amplifier **214** nor has a negative impact on the sense amplifier **214**.

[0242] In this case, the memory cell **215** is a static random access memory (SRAM) cell. Alternatively, the memory cell **215** may be a dynamic random access memory (DRAM) cell, an erasable programmable read only memory (EPROM) cell, an electronic erasable programmable read only memory (EEPROM) cell, a flash memory cell, a read only memory (ROM) cell, or a magnetic random access memory (MRAM) cell, which is connected to one or more logic gates **22**, **23** and **24** through a thick metal traces **83**, **831** or **832** over the passivation layer **5**, as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D. A sense amplifier **214**, tri-state buffer **213**, pass gate **216**, latch memory **217** or internal driver **212**, as shown in FIGS. **5**F-**5**J, may be optionally set on the path between any kind of memory cell **215** and the thick metal traces **83**, **831** or **832** over the passivation layer **5**.

[0243] In case of SDRAM cell acting as the memory cell **215**, a plurality of the memory cell **215** may be arranged in an array. A plurality of bit line **2171** and bit (bar) line **2172** arranged in parallel are connected to the sources or drains of NMOS transistors **2120** and **2119** of the memory cells **215** arranged in a column, respectively. A plurality of word line arranged in parallel and in vertical to the bit line **2171** and bit (bar) line **2172** is connected to the gate of NMOS transistors **2120** and **2119** of the memory cells **215** arranged in a row. The memory cell **215** further includes two PMOS transistors **2116** and **2118** and two NMOS transistors **2115** and **2117**, and the gates of the PMOS transistor **2116** and the NMOS transistor **2115** and the drains of the PMOS transistor **2118** and the NMOS transistor **2117** are connected t to the bit line **2171** through the channel of the NMOS transistor **2120**, and the gates of the PMOS transistor **2118** and the NMOS transistor **2117** and the drains of the PMOS transistor **2116** and the NMOS transistor **2115** are connected to the bit (bar) line **2172** through the channel of the NMOS transistor **2119**.

[0244] The sense amplifier **214**, such as differential amplifier, can be coupled to multiple memory cells **215** arranged in a column through the bit line **2171** and the bit (bar) line **2172**. The sense amplifier **214** includes two PMOS transistors **2112** and **2114** and two NMOS transistors **2111** and **2113**, and the gates of the PMOS transistors **2112** and **2114** are connected to the drains of the NMOS transistor **2111** and the PMOS transistor **2112**, and the drains of the PMOS transistor **2114** and the NMOS transistor **2113** serving as an output node of the sense amplifier **214** are connected to the gates of the PMOS transistor **2108** and the NMOS transistor **2107** in the previously described tri-state buffer **213**. The gate of the NMOS transistor **2113** is connected to the bit line **2171**. The gate of the NMOS transistor **2111** is connected to the bit (bar) line **2172**. The description and specification of the tri-state buffer **213** may be referred to the above illustration shown in FIG. **5**E.

[0245] Referring to FIG. **5**F, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214** and the source of the PMOS transistor **2108** of the tri-state output buffer **213** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214** and the source of the NMOS transistor **2107** of the tri-state output buffer **213** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The differential sense amplifier **214** is isolated from Vss by a transistor **2121**, and controlled by a column selection signal (CS**2**) to save power consumption. The transistor **2121** is turned off when the memory cell **215** is not read. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0246] When the memory cell **215** is in a "READ" operation with the NMOS transistors **2120** and **2119** being turned on, the state latched in the memory cell **215**, such as bit data and bit (bar) data, may be output to the bit line **2171** and bit (bar) line **2172** through the channels of the NMOS transistors **2120** and **2119**, respectively. The bit data and bit (bar) data

may be transmitted to the sense amplifier **214** through the bit line **2171** and bit (bar) line **2172**, respectively, to initially amplify the bit data and the bit (bar) data, leading the bit data and the bit (bar) data to have a desirable waveform or voltage level. The initially amplified bit data or bit (bar) data output from the amplifier **214** may be transmitted to a tri-state output buffer **213** to further amplify the initially amplified bit data or bit (bar) data, but FIG. **5**F only show the initially amplified bit (bar) data output from the amplifier **214** is transmitted to the input node Xi of the tri-state output buffer **213**. Further amplified bit (bar) data or bit data output from a tri-state buffer can be transmitted to the internal circuits **22**, **23** and **24** through the thick metal planes or buses **83**, **831** or **832**, as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, but FIG. **5**F only show the further amplified bit data is output from the tri-state output buffer **213**.

[0247] The bit line **2171** and bit (bar) line **2172** may be provided by fine-line metal layers, made of sputtered aluminum or damascene copper, only under the passivation layer **5**. Alternatively, the bit line **2171** and bit (bar) line **2172** may be provided by the interconnecting structure over the passivation layer **5** and under the passivation layer **5**, and the portion under the passivation layer **5** may include sputtered aluminum layer or damascene copper layer having a thickness of between 0.01 and 2 microns, and the portion over the passivation layer **5** may include electroplated copper or electroplated gold having a thickness of between 2 and 20 microns.

[0248] In this case, the thick metal buses or traces **83**, **831** or **832** shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D may be called as bit buses to transmit further amplified bit data or bit (bar) data with 4 bits width, 8 bits width, 16 bits width, 32 bits width, 64 bits width, 128 bits width, 256 bits width, 512 bits width, 1024 bits width, 2048 bits width or 4096 bits width, output from the tri-state buffers **213**. Accordingly, 4, 8, 16, 32, 64, 128, 256, 512, 1024, 2048 or 4098 bit buses arranged in parallel and over the passivation layer **5**, may connect the output nodes Xo of multiple internal circuits **21**, the tri-state buffers **213** in this case, to multiple internal circuits **22**, **23** and **24**, such as NOR gates, NAND gates, AND gates, OR gates, operational amplifiers, adders, multiplexers, diplexers, multipliers, A/D converters, D/A converters, CMOS transistors, bipolar CMOS transistors or bipolar circuits.

[0249] Alternatively, multiple address buses **85** connecting an address decoder **205** and the outputs of multiple internal circuits **25** and **26** can be formed over the passivation layer **5**, as shown in FIG. **5**U, to transmit an address data from one of the internal circuits **25** and **26** to the address decoder **205** during a "READ" operation, and the internal circuits **25** and **26** may be NOR gate, NAND gate, AND gate, OR gate, operational amplifier, adder, multiplexer, diplexer, multiplier, A/D converter, D/A converter, CMOS transistor, bipolar CMOS transistor or bipolar circuit. The address decoder **205** is connected to multiple word lines coupled with multiple memory cells in a memory array. Referring to FIGS. **5**F and **5**U, one of the word lines **2175** is connected to the gates of the NMOS transistors **2120** and **2119** of the memory cell **115**, transmitting a signal from the address decoder **205** to the memory cell to control whether the logic level of bit data saved in the trace connecting the drains of the PMOS transistor **2118** and NMOS transistor **2117** and the gates of the PMOS transistor **2116** and NMOS transistor **2115** and the logic level of bit (bar) data saved in the trace connecting the drains of the PMOS transistor **2116** and NMOS transistor **2115** and the gates of the PMOS transistor **2118** and NMOS transistor **2117** are transmitted to the bit line **2171** and the bit (bar) line **2172** through the channels of the NMOS transistors **2120** and **2119**, respectively. The sense amplifier **214** receives the bit data and bit (bar) data and initially amplifies the bit (bar) data. The initially amplified the bit (bar) data output from the sense amplifier **214** may be transmitted to the gates of the PMOS transistor **2108** and NMOS transistor **2107** of the tri-state buffer **213** through the trace **2179** under the passivation layer **5**. Two traces **2177** and **2178** connect the address decoder **205** and the tri-state buffer **213**, transmitting an ENABLE signal and an ENABLE (bar) signal from the address decoder **205** to the tri-state buffer **213** to control whether the previously described further amplified bit signal is output from the tri-state buffer **213** to the data bus **83** over the passivation layer **5**.

[0250] Other embodiments as described below can be alternatively attained. Same reference numbers in this patent application indicate same or similar elements.

[0251] Referring to FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, the internal circuit **21** may be a pass gate **216** as shown in FIG. **5**G. The pass gate **216** may include an NMOS transistor **2124** having a gate connected to an address decoder **205** through a trace **2180** under the passivation layer **5**, as shown in FIG. **5**V. In a "READ" operation, the address decoder **205** receives an address data through multiple address buses **85** over the passivation layer **5**. The address decoder **205** output a READ ENABLE data to the gate of the NMOS transistor **2124** through the trace **2180** to control whether the NMOS transistor **2124** is turned on or off. When the NMOS transistor **2124** of the pass gate **216** is turned on, the initially amplified bit (bar) data output from the sense amplifier **214** can be transmitted to the data bus **83**, **831** or **832** over the passivation layer **5** through the channel of the NMOS transistor **2124**.

[0252] Referring to FIGS. **5**B, **6**B, **7**B, **7**C and **7**D, the internal circuit **21** may be a latch circuit **217** as shown in FIG. **5**H. The latch circuit **217** may temporally store the data output from the sense amplifier **214**. The latch circuit **217** includes two PMOS transistors **2901** and **2902** and two NMOS transistors **2903** and **2904**. A trace **2905** connects the gates of the PMOS transistor **2902** and NMOS transistor **2904** and the drains of the PMOS transistor **2901** and NMOS transistor **2903**. A trace **2906** connects the gates of the PMOS transistor **2901** and NMOS transistor **2903** and the drains of the PMOS transistor **2902** and NMOS transistor **2904**. The latch circuit **217** may further include two NMOS transistors **2129** and **2130** having the gates connected to an address decoder **205** through metal traces **2181** and **2182** under the passivation layer **5**, as shown in FIG. **5**W. In a "READ" operation, the address decoder **205** receives an address data through multiple address buses **85** over the passivation layer **5**. The address decoder **205** output READ ENABLE data (RE**1** and RE**2**) to the gates of the NMOS transistors **2129** and **2130** through the traces **2181** and **2182** to control whether the NMOS transistors **2129** and **2130** are turned on or off, respectively. When the NMOS transistor **2129** is turned on, the initially amplified bit (bar) data output from the sense amplifier **214** can be transmitted to the trace **2905** through the channel of the NMOS transistor **2129**. The trace **2905** latches the bit (bar) data and the trace **2906** latches the bit data. When the NMOS transistor **2130** is turned on, the bit data output from the trace **2906** of the latch circuit **217** can be transmitted to the data bus **83**, **831** or **832** through the channel of the NMOS transistor **2130**.

[0253] Referring to FIG. **5**H, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214** and the sources of the PMOS transistors **2901** and **2902** of the latch circuit **217** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214** and the sources of the NMOS transistors **2903** and **2904** of the latch circuit **217** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0254] However, the pass gate **216** in FIG. **5**G or the latch circuit **217** in FIG. **5**H does not provide large drive capability. To drive heavy load of the logic circuits **22**, **23** and **24**, or to transmit bit (bar) data output from the pass circuit **216** or bit data output from the latch circuit **217** to the logic circuits **22**, **23** and **24** in a long distance, the internal circuit **21** may include the previously described internal driver **212** connected to the output node of the pass gate **216**, as shown in FIG. **5**I, or connected to the output node of the latch circuit **217**, as shown in FIG. **5**J, to amplify bit (bar) data output from the pass gate **216** or bit data output from the latch circuit **217**. Referring to FIG. **51**, the amplified bit (bar) data output from the internal driver **212** may be transmitted to the internal circuits **22**, **23** and **24** through the data bus **83**, **831** or **832** over the passivation layer **5**, as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D. Referring to FIG. **5**J, the amplified bit data output from the internal driver **212** may be transmitted to the internal circuits **22**, **23** and **24** through the data bus **83**, **831** or **832** over the passivation layer **5**, as shown in FIGS. **5**B, **6**B, **7**B, **7**C and **7**D.

[0255] Referring to FIG. **51**, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214** and the sources of the PMOS transistors **2104'** and **2104** of the internal driver **212** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214** and the sources of the NMOS transistors **2103'** and **2103** of the driver circuit **212** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0256] Referring to FIG. **5**J, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214**, the sources of the PMOS transistors **2901** and **2902** of the latch circuit **217** and the sources of the PMOS transistors **2104'** and **2104** of the internal driver **212** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214**, the sources of the NMOS transistors **2903** and **2904** of the latch circuit **217** and the sources of the NMOS transistors **2103'** and **2103** of the internal driver **212** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0257] Alternatively, referring to FIG. **5**K, the output node Wo of the internal circuit **24** is connected to the input nodes Xi, Ui and Vi of the internal circuits **21**, **22** and **23** through the thick metal plane, bus, trace or line **83'** over the passivation layer **5**. The internal circuit **24**, such as NOR gate, may send a signal or data from the output node Wo thereof to the input node Xi' of the internal circuit **21**, such as a receiver **212'** shown in FIG. **5**L, a tri-state input buffer **213'** shown in FIG. **5**M or other internal circuits, through a fine-line metal structure **634'** under the passivation layer **5**, then through an opening **534'** in the passivation layer **5**, then through the thick metal plane, line or trace **83'** over the passivation layer **5**, then through another opening **531'** in the passivation layer **5**, and

then through a fine-line metal structure **631'** under the passivation layer **5**. Besides, a signal or data output from the output node Wo of the internal circuit **24** may be also transmitted to the input node Ui of the internal circuit **22**, such as NOR gate, through the fine-line metal structure **634'** under the passivation layer **5**, then through the opening **534'** in the passivation layer **5**, then through the thick metal plane, line or trace **83'** over the passivation layer **5**, then through another opening **532'** in the passivation layer **5**, then through the fine-line metal structures **632***a*' and **632***b*' under the passivation layer **5**. Besides, a signal or data output from the output node Wo of the NOR gate **24** may be also transmitted to the input node Vi of the internal circuit **23**, such as NAND gate, through the fine-line metal structure **634'** under the passivation layer **5**, then through the opening **534'** in the passivation layer **5**, then through the thick metal plane, line or trace **83'** over the passivation layer **5**, then through another opening **532'** in the passivation layer **5**, then through the fine-line metal structures **632***a*' and **632***c*' under the passivation layer **5**.

[0258] The fine-line metal structures **634'**, **632'** and **631'** can be formed with stacked metal plugs, having a similar structure of the fine line metal structures **634**, **632** and **631**, respectively, as shown in **7**B, **7**C and **7**D. The internal circuits **21**, **22** and **23** may receive a signal output from the output node Wo of the internal circuit **24** at the input node Xi', Ui and Vi thereof, and may output a signal from the output node Xo', Uo and Vo thereof to other internal circuits through metal traces under the passivation layer **5**.

[0259] The structure over the passivation layer **5** shown in FIGS. **7**B-**7**D, providing the previously described thick metal trace, line or plane **83**, can also be applied to forming the thick metal trace, line or plane **83'** illustrated in FIG. **5**K. All combinations for the polymer layers **99**, **98** and **95** and the circuit metal layers **831** and **832** illustrated in FIGS. **7**B-**7**D can be applied to the combinations for one or more polymer layers and one or more circuit metal layers over the passivation layer **5**, illustrated in FIG. **5**K.

[0260] In a case, the internal circuit **21** may be an internal receiver **212'** as shown in FIG. **5**L, or an internal input tri-state buffer **213'** as shown in FIG. **5**M. Referring to FIGS. **5**K and **5**L, the internal receiver **212'** may receive a signal passing through the thick metal trace or bus **83** over the passivation layer **5** and then may output an amplified signal from the output node Xo' thereof to other internal circuits but not to an external circuit through a metal trace under the passivation layer **5**. Referring to FIGS. **5**K and **5**M, the internal input tri-state buffer **213'** may receive a signal passing through the thick metal trace or bus **83** over the passivation layer **5** and then may output an amplified signal from the output node Xo' thereof to other internal circuits but not to an external circuit through a metal trace under the passivation layer **5**.

[0261] The internal receiver **212'** in FIG. **5**L has a similar circuit design to the internal driver **212** in FIG. **5**D. In FIGS. **5**D and **5**L, same reference numbers indicate same elements with same characteristics. The internal input tri-state buffer **213'** in FIG. **5**M has a similar circuit design to the internal output tri-state buffer **213** in FIG. **5**E. In FIGS. **5**E and **5**M, same reference numbers indicate same elements with same characteristics.

[0262] The output node Xo' of the internal receiver **212'** or internal tri-state input buffer **213'** is not connected to an external circuit but connected to an internal circuit under the passivation layer **5**. The internal tri-state input buffer **213'** provides amplifying capability and switch capability, and is particularly useful to amplify a data signal or an address signal having passed through the thick metal lines or traces **83'** over the passivation layer **5** acting as data or address buses.

[0263] In FIG. **5**K, a relatively large output current is required at the output node Xo' of the internal circuit **21** when a heavy load is demanded by an internal circuit connected to the output node Xo' of the internal circuit **21**, or when the internal circuit **24** is far away from the internal circuit **21** in a distance of larger than 1 mm or of larger than 3 mm. To provide a relatively large output current, the internal circuit **21** can be designed as an internal receiver **212'** shown in FIG. **5**L or an internal tri-state input buffer **213'** shown in FIG. **5**M.

[0264] Referring to FIG. **5**K, a signal output from the internal circuit **24** can be transmitted to an n-channel MOS transistor of the internal circuit **21**, and the n-channel MOS transistor may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to **20**, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2. Alternatively, a signal output from the internal circuit **24** can be transmitted to a p-channel MOS transistor of the internal circuit **21**, and the p-channel MOS transistor **2102** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. In this application, the current level output from the internal circuit **24** and transmitted through the thick metal trace **83'** over the passivation layer **5** is, for example, in a range of between 50 μA and 2 mA, and preferably of between 100 μA and 1 mA.

[0265] In FIGS. **5**L and **5**M, the n-channel MOS transistors **2103**, **2107** and **2107'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 1.5 to 30, and preferably ranging from, e.g., about 2.5 to 10. The p-channel MOS transistors **2104**, **2108** and **2108'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 3 to 60, and preferably ranging from, e.g., about 5 to 20. In FIG. **5**L, the n-channel MOS transistor **2103'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 to 20, ranging from, e.g., about 0.1 to 10, or preferably ranging from, e.g., about 0.2 to 2, and the p-channel MOS transistor **2104'** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 to 40, ranging from, e.g., about 0.2 to 20, or preferably ranging from, e.g., about 0.4 to 4. Referring to FIGS. **5**K, **5**L and **5**M, the internal receiver **212** or internal tri-state input buffer **213** may receive a signal output from the output node Wo of the internal circuit **24** and transmitted through the thick metal trace or bus **83'** over the passivation layer **5** but not to an external circuit. A current passing through the thick metal trace or line **83'** over the passivation layer **5** and inputting the node Xi' of the internal circuit **21**, provided by the internal driver **212** or internal tri-state buffer **213**, may be between 500 μA and 10 mA, and preferably between 700 μA and 2 mA.

[0266] The concept shown in FIG. **5**K can be applied to a memory chip, as illustrated in FIGS. **5**N-**5**R. The memory chip includes memory cells **215** and sense amplifiers **214** that can be referred to those illustrated in FIG. **5**F. In FIGS. **5**F and **5**N-**5**R, same reference numbers indicate same elements.

[0267] Referring to FIG. **5**N, the previously described tri-state input buffer **213'** is employed to be the internal circuit **21** shown in FIGS. **5**K and has an output node Xo' connected to the bit (bar) line **2172** and an input node Xi' connected to the

internal circuits **22**, **23** and **24**, such as logic gates, through the above mentioned thick metal plane, bus or trace **83'** over the passivation layer **5**, and the internal circuit **24** may alternatively be NOR gate, NAND gate, AND gate, OR gate, operational amplifier, adder, multiplexer, diplexer, multiplier, A/D converter, D/A converter, CMOS transistor, bipolar CMOS transistor or bipolar circuit.

[0268] In this case, the memory cell **215** is a static random access memory (SRAM) cell. Alternatively, the memory cell **215** may be a dynamic random access memory (DRAM) cell, an erasable programmable read only memory (EPROM) cell, an electronic erasable programmable read only memory (EEPROM) cell, a flash memory cell, a read only memory (ROM) cell, or a magnetic random access memory (MRAM) cell, which is connected to the output node Wo of the logic gate **24** through a thick metal traces **83'** over the passivation layer **5**. A tri-state input buffer **213'**, pass gate **216'**, latch memory **217'** or internal receiver **212'**, as shown in FIGS. **5**N-**5**R, may be optionally set on the path between any kind of the exampled memory cell **215** and the thick metal traces **83'** over the passivation layer **5**.

[0269] Referring to FIG. **5**N, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214** and the source of the PMOS transistor **2108** of the tri-state input buffer **213'** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214** and the source of the NMOS transistor **2107** of the tri-state input buffer **213'** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0270] Referring to FIG. **5**N, when the memory cell **215** is in a "WRITE" operation, a bit signal can be transmitted to the input node Xi' of the tri-state input buffer **213'**, that is, the gates of the PMOS transistors **2108** and the NMOS transistor **2107**, through the thick metal line, trace or plane **83'** over the passivation layer **5**, from the output node Wo of the internal circuit **24**. An amplified bit (bar) signal having a desirable waveform or voltage level can be output from the output node Xo' of the tri-state input buffer **213'**, that is, the source of the PMOS transistor **2108'** or the source of the NMOS transistor **2107'**, to the bit (bar) line **2172**. With the NMOS transistors **2122** and **2119** being turned on, the bit (bar) signal on the bit (bar) line can be saved on the trace connecting the gates of the PMOS transistor **2118** and NMOS transistor **2117** and the sources of the PMOS transistor **2116** and NMOS transistor **2115**, and the bit signal can be saved on the trace connecting the gates of the PMOS transistor **2116** and NMOS transistor **2115** and the sources of the PMOS transistor **2118** and NMOS transistor **2117**.

[0271] In this case, the thick metal buses or traces **83'** may be called as bit buses to transmit to-be-written bit data or bit (bar) data with 4 bits width, 8 bits width, 16 bits width, 32 bits width, 64 bits width, 128 bits width, 256 bits width, 512 bits width, 1024 bits width, 2048 bits width or 4096 bits width, output from the tri-state buffers **213**. Accordingly, 4, 8, 16, 32, 64, 128, 256, 512, 1024, 2048 or 4098 bit buses arranged in parallel and over the passivation layer **5**, may connect the input nodes Xi' of multiple internal circuits **21**, the tri-state input buffers **213'** in this case, to multiple output nodes of multiple internal circuits **24**, such as NOR gates, NAND gates, AND gates, OR gates, operational amplifiers, adders, multiplexers, diplexers, multipliers, A/D converters, D/A converters, CMOS transistors, bipolar CMOS transistors or bipolar circuits.

[0272] Alternatively, multiple address buses **85** connecting an address decoder **205** and the outputs of multiple internal circuits **25** and **26** can be formed over the passivation layer **5**, as shown in FIG. **5**X, to transmit an address data from one of the internal circuits **25** and **26** to the address decoder **205** during a "WRITE" operation, and the internal circuits **25** and **26** may be NOR gate, NAND gate, AND gate, OR gate, operational amplifier, adder, multiplexer, diplexer, multiplier, A/D converter, D/A converter, CMOS transistor, bipolar CMOS transistor or bipolar circuit. The address decoder **205** is connected to multiple word lines coupled with multiple memory cells in a memory array. Referring to FIGS. **5**N and **5**X, one of the word lines **2175** is connected to the gates of the NMOS transistors **2120** and **2119** of the memory cell **115**, transmitting a signal from the address decoder **205** to the memory cell to control whether the logic level of bit data on the bit line **2171** is saved in the trace connecting the drains of the PMOS transistor **2118** and NMOS transistor **2117** and the gates of the PMOS transistor **2116** and NMOS transistor **2115** through the channel of the NMOS transistor **2120** and whether the logic level of bit (bar) data on the bit (bar) line **2172** is saved in the trace connecting the drains of the PMOS transistor **2116** and NMOS transistor **2115** and the gates of the PMOS transistor **2118** and NMOS transistor **2117** are transmitted to the bit line **2171** and the bit (bar) line **2172** through the channel of the NMOS transistor **2119**. Two traces **2177'** and **2178'** connect the address decoder **205** and the tri-state input buffer **213'**, transmitting an ENABLE signal and an ENABLE (bar) signal from the address decoder **205** to the tri-state input buffer **213'** to control whether the amplified bit (bar) signal is output from the tri-state input buffer **213'** to the bit (bar) line **2172**.

[0273] Other embodiments as described below can be alternatively attained. Same reference numbers in this patent application indicate same or similar elements.

[0274] Referring to FIGS. **5**K, the internal circuit **21** may be a pass gate **216'** as shown in FIG. **50**. The pass gate **216'** may include an NMOS transistor **2124'** having a gate connected to an address decoder **205** through a trace **2180'** under the passivation layer **5**, as shown in FIG. **5**Y. In a "WRITE" operation, the address decoder **205** receives an address data through multiple address buses **85** over the passivation layer

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5. The address decoder **205** output a WRITE ENABLE data to the gate of the NMOS transistor **2124'** through the trace **2180'** to control whether the NMOS transistor **2124'** is turned on or off. When the NMOS transistor **2124'** of the pass gate **216'** is turned on, the bit data transmitted through the thick metal line, trace or plane **83'** can be output from the pass gate **216'** to the bit line **2171** through the channel of the NMOS transistor **2124'**.

[0275] Referring to FIGS. **5**K, the internal circuit **21** may be a latch circuit **217'** as shown in FIG. **5**P. The latch circuit **217'** may temporally store the data transmitted through the thick metal line, trace or plane **83'**. The latch circuit **217'** includes two PMOS transistors **2901'** and **2902'** and two NMOS transistors **2903'** and **2904'**. A trace **2905'** connects the gates of the PMOS transistor **2902'** and NMOS transistor **2904'** and the drains of the PMOS transistor **2901'** and NMOS transistor **2903'**. A trace **2906'** connects the gates of the PMOS transistor **2901'** and NMOS transistor **2903'** and the drains of the PMOS transistor **2902'** and NMOS transistor **2904'**. The latch circuit **217'** may further include two NMOS transistors **2129'** and **2130'** having the gates connected to an address decoder **205** through metal traces **2181'** and **2182'** under the passivation layer **5**, as shown in FIG. **5**Z. In a "WRITE" operation, the address decoder **205** receives an address data output from the output nodes Ao or Bo of the internal circuit **25** or **26** through multiple address buses **85** over the passivation layer **5**. The address decoder **205** output WRITE ENABLE data (WE**1** and WE**2**) to the gates of the NMOS transistors **2129'** and **2130'** through the traces **2181'** and **2182'** to control whether the NMOS transistors **2129'** and **2130'** are turned on or off, respectively. When the NMOS transistor **2130'** is turned on, the bit (bar) data output from the internal circuit **24** through the thick metal line, trace or plane **83'**, data bus, over the passivation layer **5** can be latched in the trace **2906'** through the channel of NMOS transistor **2130'**, and the bit data is latched in the trace **2905'**. When the NMOS transistor **2129'** is turned on, the bit data latched in the trace **2905'** can be output to the bit line **2171** through the channel of the NMOS transistor **2129'**.

[0276] Referring to FIG. **5**P, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214** and the sources of the PMOS transistors **2901'** and **2902'** of the latch circuit **217** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214** and the sources of the NMOS transistors **2903'** and **2904'** of the latch circuit **217** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0277] However, the pass gate **216'** in FIG. **50** or the latch circuit **217'** in FIG. **5**P may not provide the enough sensitivity to detect a weak voltage variation at the input node of the pass gate **216'** or the latch circuit **217'** in a "WRITE" operation. To amplify the voltage level of a signal transmitted through the thick metal line, trace or plane **83'** in a long distance and output from the logic circuit **24**, the internal circuit **21** may include the previously described internal receiver **212'** connected to the input node of the pass gate **216'**, as shown in FIG. **5**Q, or connected to the input node of the latch circuit **217'**, as shown in FIG. **5**R, to amplify bit data inputting to the pass gate **216'** or to the latch circuit **217'**. Referring to FIGS.**5**Q and **5**R, the input node of the internal receiver **212'** is connected to the output node Wo of the internal circuit **24** through the thick metal line, trace or plane **83'** as shown in FIG. **5**K.

[0278] Referring to FIG. **5**Q, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214** and the sources of the PMOS transistors **2104'** and **2104** of the internal receiver **212'** through the 'previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214** and the sources of the NMOS transistors **2103'** and **2103** of the receiver circuit **212'** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0279] Referring to FIG. **5**R, the node P of the voltage regulator or converter circuit **41** can be connected to the sources of the PMOS transistors **2116** and **2118** of the memory cell **215**, the sources of the PMOS transistors **2112** and **2114** of the sense amplifier **214**, the sources of the PMOS transistors **2901'** and **2902'** of the latch circuit **217'** and the sources of the PMOS transistors **2104'** and **2104** of the internal receiver **212'** through the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit

layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The node Rs of the voltage regulator or converter circuit **41** can be connected to the sources of the NMOS transistors **2115** and **2117** of the memory cell **215**, the sources of the NMOS transistors **2111** and **2113** of the sense amplifier **214**, the sources of the NMOS transistors **2903'** and **2904'** of the latch circuit **217'** and the sources of the NMOS transistors **2103'** and **2103** of the internal receiver **212'** through the previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **7**B-**7**D may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0280] Referring to FIG. **5**S, another important application of the thick metal line, trace or plane **83** over the passivation layer **5** may be used to transport a precise analog signal. The thick metal line, trace or plane **83** has low resistance and capacitance per unit length characteristics and accordingly offers a low signal distortion of analog signals. FIG. **5**S shows a circuit design with an over-passivation metal bus, trace or line **83** connecting multiple analog circuits **21**, **22**, **23** and **24**. The design is similar to FIG. **5**B except that the internal circuits **21**, **22**, **23** and **24** are analog circuits, or mixed-mode circuits including an analog circuit and a digital circuit. The thick metal bus, trace or line **83** over the passivation layer **5** connects the analog circuits **21**, **22**, **23** and **24**. An analog signal output from the output node Yo of the analog circuit **21** can be transmitted to the input node Ui' of the internal circuit **22** through the fine-line metal structure **631** under the passivation layer **5**, then through the thick metal bus, trace or plane **83** over the passivation layer **5**, and then through the fine-line metal structures **632***a* and **632***b* under the passivation layer **5**. An analog signal output from the output node Yo of the analog circuit **21** can be transmitted to the input node Vi' of the internal circuit **23** through the fine-line metal structure **631** under the passivation layer **5**, then through the thick metal bus, trace or plane **83** over the passivation layer **5**, and then through the fine-line metal structures **632***a* and **632***c* under the passivation layer **5**. An analog signal output from the output node Yo of the analog circuit **21** can be transmitted to the input node Wi' of the internal circuit **24** through the fine-line metal structure **631** under the passivation layer **5**, then through the thick metal bus, trace or plane **83** over the passivation layer **5**, and then through the fine-line metal structure **634** under the passivation layer **5**.

[0281] The analog circuits **21**, **22**, **23** and **24** can be an operational amplifier, amplifier, pre-amplifier, a power amplifier, an analog to digital (A/D) converter, a digital to analog (D/A) converter, a pulse reshaping circuit, a switched capacitor filter, a RC filter, or other kind of analog circuits. FIG. **5**T shows a case where the internal circuit **21** in FIG. **5**S is an operational amplifier **218** with an output node Yo connected to the metal interconnection lines or traces **83** over the passivation layer **5**. The operational amplifier **218** is designed based on a CMOS technology, referring to "CMOS Digital Circuit Technology" by M. Shoji, published by Prentice-Hall, Inc, New Jersey in 1987. Differential analog signals can be input into two input nodes Yi+ and Yi− of a differential circuit **219** provided in the operational amplifier **218** and with two n-MOS transistors **2125** and **2127** and two p-MOS transistors **2126** and **2128**, and the input nodes Yi+ and Yi− are connected to the gates of the p-MOS transistors **2128** and **2126**, respectively. The sources of the p-MOS transistors **2126** and **2128** are connected to a drain of a p-MOS transistor **2132** that is controlled by a voltage at the node **2138** determined by resistance of a resistor **2134**. The output of the differential circuit **219** at the drains of the n-channel MOS transistor **2127** and the p-channel MOS transistor **2128** is connected to a gate of an n-channel MOS transistor **2135** and to a top electrode **21331** of the capacitor **2133**. An output node Yo is at a bottom electrode **21332** of the capacitor **2133**, at the drain of the n-channel MOS transistor **2135**, and at a drain of the p-channel MOS transistor **2136**. The p-MOS transistor **2136** is controlled by a voltage at the node **2138** determined by resistance of a resistor **2134**. Accordingly, the voltage at the output node Yo is controlled by what degree the n-MOS transistor **2135** is turned on and by the output of the differential circuit **219**. The capacitor **2133** are often used for an analog circuit, and are usually formed by a suitable process or processes, e.g., by a MOS capacitor (using the poly gate and the silicon substrate as two electrodes of the capacitor **2133**), or a poly-to-poly capacitor (using a first poly silicon and a second poly silicon as two electrodes of the capacitor **2133**). The capacitor **2133** may have a function to reduce a noise input from the input nodes Yi+ and Yi−. The resistor **2134** is also often used for an analog circuit, and is usually provided by an impurity-doped diffusion area with doping density of 10^{15}-$10^{17}/cm^3$, such as n well or p well, or of 10^{19}-$10^{21}/cm^3$, such as N^+ diffusion or P^+ diffusion, in the silicon substrate, and/or an impurity-doped poly silicon. The circuit shown in FIG. **5**T can output a voltage Yo proportionally amplifying the differential value of the input voltages Yi+ and Yi−.

[0282] The thick metal bus, trace or plane **83** and **83'** illustrated in FIGS. **5**B-**5**Z can be realized by forming the circuit metal layers **831** and/or **832** and the polymer layers **95**, **98** and/or **99** shown in FIGS. **7**B-**7**D, or by forming the circuit metal layers **801** and/or **802** and the polymer layers **95**, **97**, **98** and/or **99** shown in FIGS. **15**A-**21**K.

[0283] In FIGS. **5**B, **5**K, **5**S, **7**B, **7**C and **7**D, the thick metal trace, bus or plane **83** over the passivation layer **5** can be used to transport signals input to or output from the internal circuits **21**, **22**, **23** or **24**. In FIGS. **5**K, **5**S, **5**U and **5**V-**5**Z, a dotted line **5** indicates the passivation layer, coarse traces indicate traces of the over-passivation scheme **102** formed over the passivation layer **5**, and fine traces indicate traces formed under the passivation layer **5**.

Third Embodiment: Complete Architecture

[0284] Schemes or technology for forming coarse metal conductors, according to the present disclosure, can provide other advantages for IC chip. For example, the metal trace, bus or plane **83** or **83'** over the passivation layer **5** may include gold, copper, silver, palladium, rhodium, platinum, ruthenium, nickel, aluminum or solder; various kinds of contacting structures, such as solder bumps, solder pads, solder balls, gold bumps, gold pads, Pd pads, aluminum pads or wire bonding pads, can be formed on the metal trace, bus or plane **83** to connect the IC chip to an external circuit easily. An IC chip may be connected to and communicated with an external circuit. When a signal is transmitted to external circuits or

components, some off-chip circuitry is required to (1) drive the large current load of external circuits, parasitics or components, (2) detect noisy signals from the external circuits or components, and (3) prevent the internal circuits from being damaged by the surge electrical stimulus from external circuits or components.

[0285] FIGS. **8**B, **9**B and **10**B depict a schematic architecture according to a third exemplary embodiment of the present disclosure. FIG. **8**B shows a circuit diagram according to the third exemplary embodiment of the present disclosure. FIG. **9**B shows a top view realizing the circuit diagram of FIG. **8**B. FIG. **10**B shows a cross-sectional view realizing the circuit diagram of FIG. **8**B.

[0286] Referring to FIGS. **8**B, **9**B and **10**B, an off-chip buffer **42** is connected to the output node Xo of the internal circuit **21** and to the input nodes Ui, Vi and Wi of the internal circuits **22**, **23** and **24** through the metal trace, bus or plane **83**. A metal bump **89** for being connected to an external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, flexible substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, may be formed on a contact point **8310** of the redistributed metal trace **83***r*. The contact point **8310** can be connected to the original pad **6390** exposed by an opening **539** in the passivation layer **5** through the redistributed metal trace **83***r*, and the position of the contact point **8310** from a top perspective view is different from that of the original pad **6390**. The original pad **6390** is connected to the off-chip buffer **42** and to the off-chip ESD circuit **43**. A signal may be transmitted from the internal circuit **21** to an external circuit through the thick metal bus, trace or plane **83**, then through the off-chip buffer **42**, and then through the thick metal bus, trace or plane **83***r*; a signal may be transmitted from an external circuit to the internal circuits **22**, **23** and/or **24** through the thick metal traces, buses or plane **83***r*, through the off-chip buffer **42** and then through the thick metal bus, trace or plane **83**; a signal may be transmitted from the internal circuit **21** to the internal circuits **22**, **23** and/or **24** through the thick metal bus, trace or plane **83**. The total length of the metal trace **83** over the passivation layer **5**, connecting the off-chip buffer **42** to the internal circuit **24**, can be between 250 micrometers and 2.5 millimeters, preferably between 500 and 1 millimeter, and preferably between 1000 and 8000 micrometers.

[0287] The shape of the openings **531**, **532**, **534** and **539'** from a top perspective view may be round, square, rectangular or polygon. If the openings **531**, **532**, **534** and **539'** are round, the openings **531**, **532** and **534** may have a diameter of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **531**, **532** and **534** are square, the openings **531**, **532** and **534** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **531**, **532** and **534** are rectangular, the openings **531**, **532** and **534** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns, and a length of between 1 micron and 1 centimeter. If the openings **531**, **532** and **534** are polygon having more than five sides, the openings **531**, **532** and **534** have a largest diagonal length of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. Alternatively, the openings **531**, **532** and **534** have a largest transverse dimension of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. In a case, the openings **531**, **532** and **534** have a width of between 0.1 and 30 microns, with the lower portion of the openings **9531**, **9532** and **9514** in the polymer layer **95** having a width of between 20 and 100 microns.

[0288] Alternatively, referring to FIG. **8**C, the element **42** may be an off-chip receiver. The off-chip receiver **42** is connected to the input nodes of the internal circuits **21**, **22**, **23** and **24** through the thick metal bus, trace or plane **83**.

[0289] Alternatively, referring to FIG. **8**G, the element **42** may be an off-chip driver. The off-chip driver **42** is connected only to the output nodes of the internal circuits **21**, **22**, **23** and **24** through the thick metal bus, trace or plane **83**.

[0290] FIGS. **8**B and **8**C show a simplified circuit diagram where a thick metal trace **83** over a passivation layer **5** connects an off-chip buffer **42**, such as external driver or external receiver, and internal circuits **21**, **22**, **23** and **24**. FIG. **9**B shows a top view of a semiconductor chip realizing the circuitry shown in FIGS. **8**B and **8**C, and coarse traces **83** and **83***r* shown in FIG. **9**B mean the traces formed over the passivation layer **5**, and fine traces **69**, **632***a*, **632***b* and **632***c* shown in FIG. **9**B mean the traces formed under the passivation layer **5**. FIG. **10**B shows a cross-sectional view of a semiconductor chip realizing the circuitry shown in FIGS. **8**B and **8**C. FIG. **9**B shows a top view of the semiconductor chip shown in FIG. **10**B. FIGS. **8**B, **9**B, **10**B, **10**C, **10**D and **10**E show the circuitry architecture of the disclosure using the two hierarchies of the fine-line IC metal structures **639**, **639'**, **631**, **632**, **634** and **69** under the passivation layer **5** and the coarse metal traces **83**, **831**, **832** and **83***r* over the passivation layer **5**, with the consideration of whole chip design of the internal and external circuit connection.

[0291] Referring to FIGS. **8**B, **9**B and **10**B, the internal circuit **21** may output a signal to other internal circuits **22**, **23** and **24** through the thick metal bus, trace or plane **83** over the passivation layer **5**, as described in FIGS. **5**B-**5**J and **5**S-**5**T, and, besides, the internal circuit **21** may output a signal to an external circuit through, in sequence, the fine-line metal trace **631** under the passivation layer **5**, the thick metal trace **83** over the passivation layer **5**, the fine-line metal trace **639'** under the passivation layer **5**, the off-chip buffer **42**, such as external driver, the fine-line metal trace **69** under the passivation layer **5**, the redistributed trace **83***r* over the passivation layer **5** and the metal bump **89** on the redistributed trace **83***r*.

[0292] Referring to FIG. **8**C, **9**B and **10**B, a signal output from the internal circuit **24** may be transmitted to the internal circuit **21** through the thick metal bus, trace or plane **83'** over the passivation layer **5**, as described in FIGS. **5**K-**5**R, and, besides, a signal output from an external circuit may be transmitted to the internal circuit **21** through the metal bump **89**, the redistributed trace **83***r*, the fine-line metal trace **69** under the passivation layer **5**, the off-chip buffer **42**, such as external receiver, the fine-line metal trace **639'** under the passivation layer **5**, the thick metal bus, trace or plane **83'** over the passivation layer **5** and the fine-line metal trace **631'** under the passivation layer **5**. A signal output from the internal circuit **24** may be transmitted to the internal circuit **22** through the thick metal bus, trace or plane **83'** over the passivation layer **5**, as described in FIGS. **5**K-**5**R, and, besides, a signal output from an external circuit may be transmitted to the internal circuit **22** through the metal bump **89**, the redistributed trace **83***r*, the fine-line metal trace **69** under the passivation layer **5**, the off-chip buffer **42**, such as external receiver, the fine-line metal trace **639'** under the passivation layer **5**, the thick metal bus, trace or plane **83'** over the passivation layer **5**, the fine-

line metal trace **632***a*' and **632***b*'under the passivation layer **5**. A signal output from the internal circuit **24** may be transmitted to the internal circuit **23** through the thick metal bus, trace or plane **83**' over the passivation layer **5**, as described in FIGS. **5**K-**5**R, and, besides, a signal output from an external circuit may be transmitted to the internal circuit **23** through the metal bump **89**, the redistributed trace **83***r*, the fine-line metal trace **69** under the passivation layer **5**, the off-chip buffer **42**, such as external receiver, the fine-line metal trace **639**' under the passivation layer **5**, the thick metal bus, trace or plane **83**' over the passivation layer **5**, the fine-line metal trace **632***a*' and **632***c*'under the passivation layer **5**.

[0293] In this embodiment, referring to FIGS. **8**B and **8**C, a signal transmitted through the thick metal bus, trace or plane **83** or **83**' over the passivation layer **5** in the internal scheme **200** can be transmitted to or from the external circuit (not shown) through an off-chip circuit **40** including an off-chip buffer **42**, such as external driver or receiver, and an off-chip ESD (electro static discharge) circuit **43**. The off-chip ESD circuit **43** is connected in parallel with the off-chip buffer **42** through the trace **69** under the passivation layer **5**. The redistributed metal trace **83***r* can be used for redistribution of the IC fine-line metal (**1**/**0**) pads **6390** in FIG. **10**B, relocated to a different location, for example an over-passivation metal pads **8310** in FIG. **10**B, resulting in readily being connected to an external circuit, such as another semiconductor chip, ball-grid-array (BGA) substrate or ceramic substrate through the metal bump **89** or through a wirebonded wire bonded onto the pad **8310**, to a flexible substrate through the metal bump **89** preferably including a gold layer having a thickness between 7 and 25 micrometers using a gold-to-gold bonding technology or using a gold-to-tin bonding technology, or to a glass substrate through the metal bump **89** preferably including a gold layer having a thickness between 7 and 25 micrometers via an anisotropic conductive film (ACF) or anisotropic conductive paste ACP. The redistributed metal line, trace or plane **83***r* can be formed during forming the over-passivation interconnection scheme **83**.

[0294] Referring to FIG. **11**F, the off-chip circuitry **40**, in FIGS. **8**B and **8**C, for being connected to the external circuitry may include an off-chip ESD circuit **43**, composed of two diodes **4331** and **4332**, and an off-chip buffer **42**.

[0295] In a first aspect, the off-chip buffer **42** may be an off-chip driver **421**, as shown in FIG. **11**A, in application to the circuit architecture shown in FIG. **8**B, having an input node F connected to the internal circuits **20** through the thick and wide circuit trace **83**, and an output node E connected, in parallel with the off-chip ESD circuit **43**, to the metal bump **89**. FIG. **11**A shows an example of a two-stage cascade off-chip driver **421**, CMOS cascade driver. The cascade driver may include several stages of inverters. The off-chip driver **421** may include two inverters **421**' and **421**", and the inverter **421**' is composed of an NMOS device **4201** and a PMOS device **4202**, and the inverter **421**" is composed of an NMOS device **4203** and a PMOS device **4204**. The gates of the PMOS device **4202** and the NMOS device **4201** serve as the input node F, and the drains of the PMOS device **4204** and the NMOS device **4203** serve as the output node E. The drains of the PMOS device **4202** and the NMOS device **4201** are connected to the gates of the PMOS device **4204** and the NMOS device **4203**.

[0296] Referring to FIG. **11**A, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** and the sources of the PMOS devices **4202** and **4204**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the sources of the NMOS devices **4201** and **4203**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0297] The first stage **421**'of the off-chip driver in FIG. **11**A is an inverter with the NMOS device **4201** having a ratio of a physical channel width thereof to a physical channel length thereof larger than those of all NMOS devices in the internal circuits **20** connected to the input node F of the off-chip driver **421**, and with the PMOS device **4202** having a ratio of a physical channel width thereof to a physical channel length thereof larger than those of all PMOS devices in the internal circuits **20** connected to the input node F of the off-chip driver **421**. The NMOS transistor **4203** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 20,000, and preferably ranging from, e.g., about 30 to 300. The PMOS transistor **4204** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 40 to 40,000, and preferably ranging from, e.g., about 60 to 600. The output current of an off-chip driver **421** is proportional to the number of stages and the size (W/L, MOS transistor's channel width to length ratio, more precisely, the MOS effective channel width to effective channel length ratio) of transistors used in each stage of the off-chip driver. The off-chip driver **421** may output a driving current of between 5 mA and 5 A and, preferably, between 10 mA and 100 mA.

[0298] Provided that the off-chip driver **421** shown in FIG. **11**A is applied to the circuit architecture shown in FIG. **8**B for a power management chip, the NMOS transistor **4203** of the off-chip driver **421** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 2,000 to 200,000, and preferably ranging from, e.g., about 2,000 to 20,000. The PMOS transistor **4204** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 4,000 to 400,000, and preferably ranging from, e.g., about 4,000 to 40,000. The off-chip driver **421** may output a driving current of between 500 mA and 50 A and, preferably, between 500 mA and 5 A.

[0299] In a second aspect, the off-chip buffer **42** may be an off-chip receiver **422**, as shown in FIG. **11**B, in application to the circuit architecture shown in FIG. **8**C, having an output node F connected to the internal circuits **21**, **22** and **23** through the thick and wide circuit trace **83**, and an input node E connected, in parallel with the off-chip ESD circuit **43**, to the metal bump **89**. FIG. **11**B shows an example of a two-

stage cascade off-chip receiver **422**, CMOS cascade receiver. The off-chip receiver **422** may receive a signal from an external circuitry through the metal bump **89** and output an amplified signal to the internal circuits **21**, **22** and **23** through the thick and wide trace or bus **83'**. The first stage **422'**, close to the external circuitry, of the off-chip receiver **422** is an inverter having an NMOS device **4205** and a PMOS device **4206** with a size designed to detect a noisy external signal. The first stage receives a noisy signal at point E from the external circuits or components, such as signal from another chip. The second stage **422"** of the off-chip receiver **422** is also an inverter except that it is formed by a suitable process or processes, e.g., by a larger size of NMOS device **4207** and PMOS device **4208**. The second stage of the inverter is used to restore the integrity of the noisy external signal for the internal circuit. The gates of the PMOS device **4205** and the NMOS device **4206** serve as the input node E, and the drains of the PMOS device **4208** and the NMOS device **4207** serve as the output node F. The drains of the PMOS device **4206** and the NMOS device **4205** are connected to the gates of the PMOS device **4208** and the NMOS device **4207**.

[0300] Referring to FIG. **11**B, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** and the sources of the PMOS devices **4206** and **4208**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the sources of the NMOS devices **4205** and **4207**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0301] The first stage **422'**of the off-chip receiver in FIG. **11**B is an inverter with the NMOS device **4205** having a ratio of a physical channel width thereof to a physical channel length thereof larger than those of all NMOS devices in the internal circuits **20** connected to the output node F of the off-chip receiver **422**, and with the PMOS device **4206** having a ratio of a physical channel width thereof to a physical channel length thereof larger than those of all PMOS devices in the internal circuits **20** connected to the output node F of the off-chip receiver **422**. The NMOS transistor **4207** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 10 to 20,000, and preferably ranging from, e.g., about 10 to 300. The PMOS transistor **4208** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 40,000, and preferably ranging from, e.g., about 20 to 600. The off-chip receiver **422** may output a driving current of between 2 mA and 5 A and, preferably, between 3 mA and 100 mA.

[0302] Provided that the off-chip receiver **422** shown in FIG. **11**B is applied to the circuit architecture shown in FIG. **8**C for a power management chip, the NMOS transistor **4207** of the off-chip receiver **422** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 10 to 20,000, and preferably ranging from, e.g., about 10 to 300. The PMOS transistor **4208** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 40,000, and preferably ranging from, e.g., about 20 to 600. The off-chip receiver **422** may output a driving current of between 150 mA and 50 A and, preferably, between 150 mA and 5 A.

[0303] In a third aspect, the off-chip buffer **42** may be a tri-state buffer **423**, as shown in FIG. **11**C, in application to the circuit architecture shown in FIG. **8**B, having an input node F connected to the internal circuits **20** through the thick and wide circuit trace **83**, and an output node E, in parallel with the off-chip ESD circuit **43**, connected to the metal bump **89**. FIG. **11**C shows an example of an off-chip tri-state buffer **423**; as an off-chip driver, a common design in IC chips to allow multiple logic gates to drive the same output, such as a bus. The tri-state buffer **423**, serving as an off-chip driver, may include two PMOS devices **4210** and **4212** and two NMOS devices **4209** and **4211**. The gates of the PMOS device **4210** and the NMOS device **4209** serve as the input node F, and the drains of the PMOS device **4212** and the NMOS device **4211** serve as the output node E. The drain of the PMOS device **4210** is connected to the source of the PMOS device **4212**. The drain of the NMOS device **4209** is connected to the source of the NMOS device **4211**. The tri-state buffer **423** may have a switch function controlled by an Enable signal transmitted to the gate of the NMOS device **4211** and an Enable(bar) signal transmitted to the gate of the PMOS device **4212**. The off-chip tri-state buffer in FIG. **11**C can be viewed as a gated inverter. When the enabling signal En is high (En is low), the off-chip tri-state buffer outputs a signal to an external circuit. When the signal En is set at low ($\overline{\text{En}}$ is high), no signal will be output to an external circuit. The off-chip tri-state buffer **423** is set to drive the external data bus.

[0304] Referring to FIG. **11**C, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** and the source of the PMOS device **4210**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the source of the NMOS device **4209**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0305] The NMOS transistors **4209** and **4211** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 20,000, and preferably ranging from, e.g., about 30 to 300. The PMOS transistors **4210** and **4212** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 40 to 40,000, and preferably ranging from, e.g., about 60 to 600. The tri-state buffer **423** may output a driving current of between 5 mA and 5 A and, preferably, between 10 mA and 100 mA.

[0306] Provided that the tri-state buffer **423** shown in FIG. **11**A is applied to the circuit architecture shown in FIG. **8**B for a power management chip, the NMOS transistors **4209** and **4211** of the tri-state buffer **423** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 2,000 to 200,000, and preferably ranging from, e.g., about 2,000 to 20,000. The PMOS transistors **4210** and **4212** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 4,000 to 400,000, and preferably ranging from, e.g., about 4,000 to 40,000. The tri-state buffer **423** may output a driving current of between 500 mA and 50 A and, preferably, between 500 mA and 5 A.

[0307] In a fourth aspect, the off-chip buffer **42** may be a tri-state buffer **423**, as shown in FIG. **11**E, in application to the circuit architecture shown in FIG. **8**C, having an output node F connected to the internal circuits **21**, **22** and **23** through the thick and wide circuit trace **83'**, and an input node E, in parallel with the off-chip ESD circuit **43**, connected to the metal bump **89**. FIG. **11**E shows an example of an off-chip tri-state buffer **423**, as an off-chip receiver. The tri-state buffer **423**, serving as an off-chip receiver, may include two PMOS devices **4210** and **4212** and two NMOS devices **4209** and **4211**. The gates of the PMOS device **4210** and the NMOS device **4209** serve as the input node E, and the drains of the PMOS device **4212** and the NMOS device **4211** serve as the output node F. The drain of the PMOS device **4210** is connected to the source of the PMOS device **4212**. The drain of the NMOS device **4209** is connected to the source of the NMOS device **4211**. The tri-state buffer **423** may have a switch function controlled by an Enable signal transmitted to the gate of the NMOS device **4211** and an Enable (bar) signal transmitted to the gate of the PMOS device **4212**. When the enabling signal En is high ($\overline{\text{En}}$ is low), the off-chip tri-state buffer outputs a signal to the internal circuits **20**. When the signal En is set at low ($\overline{\text{En}}$ is high), no signal will be output to the internal circuits **20**.

[0308] Referring to FIG. **11**E, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** and the source of the PMOS device **4210**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**D and **10**G may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the source of the NMOS device **4209**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layers **831** and/or **832** of the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIGS. **10**B-**10**E and **10**G may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0309] The NMOS transistors **4209** and **4211** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 20,000, and preferably ranging from, e.g., about 30 to 300. The PMOS transistors **4210** and **4212** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 40 to 40,000, and preferably ranging from, e.g., about 60 to 600. The tri-state buffer **423** may output a driving current of between 5 mA and 5 A and, preferably, between 10 mA and 100 mA.

[0310] Provided that the tri-state buffer **423** shown in FIG. **11**E is applied to the circuit architecture shown in FIG. **8**C for a power management chip, the NMOS transistors **4209** and **4211** of the tri-state buffer **423** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 2,000 to 200,000, and preferably ranging from, e.g., about 2,000 to 20,000. The PMOS transistors **4210** and **4212** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 4,000 to 400,000, and preferably ranging from, e.g., about 4,000 to 40,000. The tri-state buffer **423** may output a driving current of between 500 mA and 50 A and, preferably, between 500 mA and 5 A.

[0311] There may be various off-chip input and output buffers. The above examples are for the CMOS level signals. If the external signal is a transistor-transistor logic (TTL) level, a CMOS/TTL buffer is required. If the external signal is an emitter coupled logic (ECL) level, a CMOS/ECL interface buffer is required. One or more stages of inverters can be added between the internal circuits **20** and the off-chip tri-state buffer **423** serving as an off-chip driver as shown in FIG. **11**C or as an off-chip receiver as shown in FIG. **11**E.

[0312] In a fifth aspect, the off-chip buffer **42** may be an off-chip driver **421** composed of a first level of inverter **421'** and a second level of inverters **421"**, as shown in FIG. **11**D, in application to the circuit architecture shown in FIG. **8**B, and the first level of inverter **421'** is connected in series to the second level of inverters **421"**, and the second level of inverters **421"** are connected in parallel with one another to the first level of inverter **421'**. FIG. **8**E shows a circuit diagram with the off-driver **421** of FIG. **11**D applied to the circuit architecture shown in FIG. **8**C. FIG. **9**C shows a top perspective view realizing the circuit diagram of FIG. **8**E. FIG. **10**H shows a chip structure realizing the circuit diagram of FIG. **8**E. The off-chip driver **421** has an input node F connected to the internal circuits **20** through the thick and wide circuit trace **83**, and an output node E connected, in parallel with the off-chip ESD circuit **43**, to the metal bump **89**. The gates of the PMOS device and the NMOS device in the first level of inverter **421'** serve as the input node F, and the drains of the PMOS devices and the NMOS devices in the second level of inverters **421"** serve as the output node E. The drains of the PMOS device and the NMOS device in the first level of inverter **421'** are connected to the gates of the PMOS devices and the NMOS devices in the second level of inverters **421"** through a thick and wide metal trace or bus **83**s over the passivation layer **5**. The drains of the PMOS devices and the NMOS devices in the

second level of inverters **421"** are connected to the metal bump **89** through a thick and wide metal trace or bus **83***r* over the passivation layer **5**. A patterned circuit layer **831** formed on the polymer layer **95**, such as polyimide, having a thickness of between 2 and 30 micrometers may be composed of the thick and wide metal traces or buses **83***r*, **83***s* and **83**, that is, the thick and wide metal traces or buses **83***r*, **83***s* and **83** may be formed at the same time, as shown in FIG. **10**H.

[0313] Alternatively, multiple patterned circuit layers and multiple polymer layers may be formed over the passivation layer **5**, one of the polymer layers is between neighboring two of the patterned circuit layers. The thick and wide metal traces or buses **83***s* may be formed in the lower one of the patterned circuit layers, and the thick and wide metal traces or buses **83***s* may be formed in the upper one of the patterned circuit layers and over the thick and wide metal traces or buses **83***s*. The thick and wide metal traces or buses **83** may have a portion in the lower one of the patterned circuit layers and another portion in the upper one of the patterned circuit layers.

[0314] Referring to FIG. **11**D, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** to the source of the PMOS device in the first level of inverter **421'** and to the sources of the PMOS devices in the second level of inverter **421"**. The previously described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layer **831** of the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**H. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**H may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41**, the source of the NMOS device in the first level of inverter **421'**, and the sources of the NMOS devices in the second level of inverters **421"**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layer **831** of the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**H. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**H may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0315] Each of the NMOS transistors in the second level of inverters **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 20,000, and preferably ranging from, e.g., about 30 to 300, larger than that of NMOS transistor in the first level inverter **421'** by between 1.5 times and 5 times, and preferably by natural exponential times. Each of the PMOS transistors in the second level of inverters **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 40 to 40,000, and preferably ranging from, e.g., about 60 to 600, larger than that of PMOS transistor in the first level inverter **421'** by between 1.5 times and 5 times, and preferably by natural exponential times. The off-chip driver **421** may output a driving current of between 5 mA and 5 A and, preferably, between 10 mA and 100 mA to an external circuit through the metal bump **89**.

[0316] Provided that the off-chip driver **421** shown in FIG. **11**D is applied to the circuit architecture shown in FIG. **8**B for a power management chip, each of the NMOS transistors in the second level of inverters **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 2,000 to 200,000, and preferably ranging from, e.g., about 2,000 to 20,000. Each of the PMOS transistors in the second level of inverters **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 4,000 to 400,000, and preferably ranging from, e.g., about 4,000 to 40,000. The off-chip driver **421** may output a driving current of between 500 mA and 50 A and, preferably, between 500 mA and 5 A to an external circuit through the metal bump **89**.

[0317] In a sixth aspect, the off-chip buffer **42** may be an off-chip driver **421** composed of a first level of inverter **421'**, a second level of inverters **421"**, a third level of inverter **421'"** and a fourth level of inverter **421'"**, as shown in FIG. **11**G, in application to the circuit architecture shown in FIG. **8**B, and the first level of inverter **421'** is connected in series to the second level of inverters **421"**, the second level of inverter **421"** is connected in series to the third level of inverters **421'"**, and the third level of inverter **421'** is connected in series to the fourth level of inverters **421""**. FIG. **8**F shows a circuit diagram with the off-driver **421** of FIG. **11**G applied to the circuit architecture shown in FIG. **8**C: FIG. **9**D shows a top perspective view realizing the circuit diagram of FIG. **8**F. FIG. **10**I shows a chip structure realizing the circuit diagram of FIG. **8**F. The off-chip driver **421** has an input node F connected to the internal circuits **20** through the thick and wide circuit trace **83**, and an output node E connected, in parallel with the off-chip ESD circuit **43**, to the metal bump **89**. The gates of the PMOS device and the NMOS device in the first level of inverter **421'** serve as the input node F, and the drains of the PMOS device and the NMOS device in the fourth level of inverter **421""** serve as the output node E. The drains of the PMOS device and the NMOS device in the first level of inverter **421'** are connected to the gates of the PMOS device and the NMOS device in the second level of inverter **421"** through a fine-line metal trace or bus under the passivation layer **5**. The drains of the PMOS device and the NMOS device in the second level of inverter **421"** are connected to the gates of the PMOS device and the NMOS device in the third level of inverter **421'"** through a fine-line metal trace or bus under the passivation layer **5**. The drains of the PMOS device and the NMOS device in the third level of inverter **421'"** are connected to the gates of the PMOS device and the NMOS device in the fourth level of inverter **421""** through a fine-line metal trace or bus under the passivation layer **5**. The drains of the PMOS device and the NMOS device in the fourth level of inverters **421""** are connected to the metal bump **89** through the thick and wide metal trace or bus **83***r* over the passivation layer **5**. A patterned circuit layer **831** formed on the polymer layer **95**, such as polyimide, having a thickness of between 2 and 30 micrometers may be composed of the thick and wide metal traces or buses **83***r* and **83**, that is, the thick and wide metal traces or buses **83***r* and **83** may be formed at the same time, as shown in FIG. **10**I.

[0318] Referring to FIG. **11**G, the previously described power plane, bus or trace **81**, **811** or **812**, as shown in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, over the passivation layer **5** can connect the node P of the voltage regulator or converter circuit **41** to the source of the PMOS device in the first level of inverter **421'**, to the source of the PMOS device in the second level of inverter **421"**, to the source of the PMOS device in the third level of inverter **421'"** and to the source of the PMOS device in the fourth level of inverter **421""**. The previously

described power plane, bus or trace **81**, **811** or **812** may contain a patterned circuit layer over the patterned circuit layer **831** of the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**I. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**I may contain a patterned circuit layer over that of the previously described power plane, bus or trace **81**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41**, the source of the NMOS device in the first level of inverter **421'**, the source of the NMOS device in the second level of inverter **421"**, the source of the NMOS device in the third level of inverter **421'"**, and the source of the NMOS device in the fourth level of inverter **421""**. The previously described ground plane, bus or trace **82** or **821** may contain a patterned circuit layer over the patterned circuit layer **831** of the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**I. Alternatively, the thick and wide signal trace, bus or plane **83** as shown in FIG. **10**I may contain a patterned circuit layer over that of the previously described ground plane, bus or trace **82**.

[0319] The NMOS transistor in the fourth level of inverter **421""** may have a ratio of a physical channel width thereof to a physical channel length thereof larger than that of the NMOS transistor in the third level of inverter **421'"** by between 1.5 and 5 times, and preferably by natural exponential times, that is larger than that of the NMOS transistor in the second level of inverter **421"** by between 1.5 and 5 times, and preferably by natural exponential times, that is larger than that of the NMOS transistor in the first level of inverter **421'** by between 1.5 and 5 times, and preferably by natural exponential times. The PMOS transistor in the fourth level of inverter **421""** may have a ratio of a physical channel width thereof to a physical channel length thereof larger than that of the PMOS transistor in the third level of inverter **421'"** by between 1.5 and 5 times, and preferably by natural exponential times, that is larger than that of the PMOS transistor in the second level of inverter **421"** by between 1.5 and 5 times, and preferably by natural exponential times, that is larger than that of the PMOS transistor in the first level of inverter **421'** by between 1.5 and 5 times, and preferably by natural exponential times. The off-chip driver **421** may output a driving current of between 5 mA and 5 A and, preferably, between 10 mA and 100 mA to an external circuit through the metal bump **89**.

[0320] The NMOS transistor in the fourth level of inverter **421""** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 20 to 20,000, and preferably ranging from, e.g., about 30 to 300. The PMOS transistor in the fourth level of inverter **421""** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 40 to 40,000, and preferably ranging from, e.g., about 60 to 600. The NMOS transistor in the third level of inverter **421'"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 7 to 7,000, and preferably ranging from, e.g., about 10 to 100. The PMOS transistor in the third level of inverter **421'"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 13 to 13,000, and preferably ranging from, e.g., about 20 to 200. The NMOS transistor in the second level of inverter **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 2 to 2,000, and preferably ranging from, e.g., about 3 to 30. The PMOS transistor in the second level of inverter **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 4 to 4,000, and preferably ranging from, e.g., about 6 to 70.

[0321] Provided that the off-chip driver **421** shown in FIG. **11**D is applied to the circuit architecture shown in FIG. **8**B for a power management chip, the NMOS transistor in the fourth level of inverter **421""** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 2,000 to 200,000, and preferably ranging from, e.g., about 2,000 to 20,000. The PMOS transistor in the fourth level of inverter **421""** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 4,000 to 400,000, and preferably ranging from, e.g., about 4,000 to 40,000. The NMOS transistor in the third level of inverter **421'"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 700 to 70,000, and preferably ranging from, e.g., about 700 to 7,000. The PMOS transistor in the third level of inverter **421'"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 1,300 to 130,000, and preferably ranging from, e.g., about 1,300 to 13,000. The NMOS transistor in the second level of inverter **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 230 to 23,000, and preferably ranging from, e.g., about 230 to 2,300. The PMOS transistor in the second level of inverter **421"** may have a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 400 to 40,000, and preferably ranging from, e.g., about 400 to 4,000. The off-chip driver **421** may output a driving current of between 500 mA and 50 A and, preferably, between 500 mA and 5 A to an external circuit through the metal bump **89**.

[0322] Referring to FIGS. **8**B, **8**C, **8**E and **8**F, the off-chip buffer **42** is connected, in parallel with the off-chip ESD circuit **43**, to the metal bump **89**. The detail of the off-chip ESD circuit **43** may be referred to as FIG. **11**F. The off-chip ESD circuit **43** is composed of two reverse-biased diodes **4331** and **4332**, and the node E is connected to the anode of the diode **4332**, to the cathode of the diode **4331**, to the off-chip buffer **42**, such as off-chip driver **421** of FIG. **11**A, **11**D or **11**G, off-chip receiver **422** of FIG. **11**B, or tri-state buffer **423** of FIG. **11**C or **11**E, and to the metal bump **89**. The diode **4331** is reverse-biased between an external voltage and the ground voltage Vss, and the diode **4332** is reverse-biased between the external voltage and the power voltage Vdd or Vcc.

[0323] Referring to FIG. **11**F, an external power voltage Vdd can be provided to the cathode of the diode **4332** through a power bus or plane over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the cathode of the diode **4331**.

[0324] Accordingly, the voltage at the node E can be clamped between the power voltage Vdd input from an external circuit and the ground voltage Vss or between the power voltage Vdd and the ground voltage Vss. When the voltage at the node E suddenly exceeds the power voltage Vdd, a current will discharge from the node E to the external circuit through the diode **4332**. When the voltage at the node E dramatically

drop under the ground voltage Vss, a current will flow from the external circuit to the node E through the diode **4331**.

[0325] Alternatively, the node E in the circuit diagrams in FIGS. **8**B, **8**C, **8**E and **8**F can be protected by multiple off-chip ESD circuits **43**, which can be referred to as FIG. **11**H. For example, referring to FIG. **8**D, the node E connecting the off-chip driver **42** to the metal bump **89** may be protected by multiple off-chip ESD circuits **43**. Each of the off-chip ESD circuits **43** is composed of two reverse-biased diodes **4331** and **4332**, and the node E is connected to the anodes of the diodes **4332**, to the cathodes of the diodes **4331**, to the off-chip buffer **42**, such as off-chip driver **421** of FIG. **11**A, **11**D or **11**G, off-chip receiver **422** of FIG. **11**B, or tri-state buffer **423** of FIG. **11**C or **11**E, and to the metal bump **89**. The diodes **4331** are reverse-biased between an external voltage and the ground voltage Vss, and the diodes **4332** are reverse-biased between the external voltage and the power voltage Vdd or Vcc.

[0326] Referring to FIG. **11**H, an external power voltage Vdd can be provided to the cathodes of the diodes **4332** through a power bus or plane over the passivation layer **5**. The previously described ground plane, bus or trace **82** or **821**, as shown in FIGS. **1**C, **2**C and **3**C, over the passivation layer **5** can connect the node Rs of the voltage regulator or converter circuit **41** and the cathodes of the diodes **4331**.

[0327] Accordingly, the voltage at the node E can be clamped between the power voltage Vdd input from an external circuit and the ground voltage Vss. When the voltage at the node E suddenly exceeds the power voltage Vdd, a current will discharge from the node E to the external circuit through the diodes **4332**. When the voltage at the node E dramatically drop under the ground voltage Vss, a current will flow from the external circuit to the node E through the diodes **4331**.

[0328] In FIGS. **10**B, **10**D, **10**G, **10**H and **10**I, there is only one patterned circuit layer **831**, including a portion serving as the previously described thick and wide metal trace **83** and another portion serving as the previously described thick and wide metal trace **83***r*, over the passivation layer **5**. The patterned circuit layer **831** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8312** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8311**.

[0329] Referring to FIG. **10**B, regards to the process for forming the patterned circuit layer **831**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on a silicon-nitride layer of the passivation layer **5** and on contact pads **6390**, principally made of aluminum or copper, exposed by multiple openings **539**, **539'**, **531**, **532** and **534** in the passivation layer **5**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8312** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8312** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8312** is removed using a wet-etching process or using a dry-etching process.

[0330] After the patterned circuit layer **831** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **831** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9939** may be formed in the polymer layer **99**, exposing the contact point **8310** of the patterned circuit layer **831**.

[0331] The process of forming the metal bump **89** on the polymer layer **99** and on the contact point **8310** exposed by the opening **9939** as shown in FIGS. **10**B and **10**D can be referred to as the process of forming the metal bumps **89** on the polymer layer **98** and on the regions **801***a* exposed by the openings **980** as illustrated in FIG. **15**M. The specification of the metal bump **89** as shown in FIGS. **10**B and **10**D can be referred to as the specification of the metal bumps **89** as illustrated in FIG. **15**M.

[0332] The metal bump **89** can be used to be connected to a printed circuit board, a ceramic substrate, another semiconductor chip, a flexible substrate by a tape-automated bonding (TAB) process, or a glass substrate via anisotropic conductive film or paste (ACF or ACP).

[0333] Alternatively, referring to FIG. **10**B, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact point **8310** exposed by the opening **9939**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9939** in the polymer layer **99**. Thereafter, a gold wire or a copper wire can be bonded

onto the electroless plated gold layer in the opening **9939** in the polymer layer **99** using a wirebonding process.

[0334] Alternatively, referring to FIG. **10**B, a gold wire or a copper wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **831**, exposed by the openings **9939** in the polymer layer **99** using a wirebonding process.

[0335] Alternatively, referring to FIG. **10**C, there may be multiple patterned circuit layers **831** and **832**, including a portion serving as the previously described thick and wide metal trace **83** and another portion serving as the previously described thick and wide metal trace **83***r*, over the passivation layer **5**. The process for forming the patterned circuit layer **831** shown in FIG. **10**C can be referred to as the process for forming the patterned circuit layer **831** shown in FIG. **10**B. The patterned circuit layer **832** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8322** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8321**.

[0336] Referring to FIG. **10**C, after the patterned circuit layer **831** is formed, a polymer layer **98** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **831** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9831**, **9834** and **9839** may be formed in the polymer layer **98**, exposing multiple contact pads of the patterned circuit layer **831**.

[0337] Referring to FIG. **10**C, regards to the process for forming the patterned circuit layer **832**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **98** and on the contact pads of the patterned circuit layer **831** exposed by multiple openings **9839**, **9831** and **9834** in the polymer layer **98**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8322** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8322** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8322** is removed using a wet-etching process or using a dry-etching process.

[0338] After the patterned circuit layer **832** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **832** and on the polymer layer **98**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9939'** may be formed in the polymer layer **99**, exposing a contact point **8320** of the patterned circuit layer **832**.

[0339] The process of forming the metal bump **89** on the polymer layer **99** and on the contact point **8320** exposed by the opening **9939'** as shown in FIGS. **10**C and **10**E can be referred to as the process of forming the metal bumps **89** on the polymer layer **98** and on the regions **801***a* exposed by the openings **980** as illustrated in FIG. **15**M. The specification of the metal bump **89** as shown in FIGS. **10**C and **10**E can be referred to as the specification of the metal bumps **89** as illustrated in FIG. **15**M.

[0340] The metal bump **89** shown in FIGS. **10**C and **10**E can be used to be connected to a printed circuit board, a ceramic substrate, another semiconductor chip, a flexible substrate by a tape-automated bonding (TAB) process, or a glass substrate via anisotropic conductive film or paste (ACF or ACP).

[0341] Alternatively, referring to FIG. **10**C, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact point **8320** exposed by the opening **9939'** in layer polymer layer **99**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9939'** in the polymer layer **99**. Thereafter, a gold wire or a copper wire can be bonded onto the electroless plated gold layer in the opening **9939'** in the polymer layer **99** using a wirebonding process.

[0342] Alternatively, referring to FIG. **10**C, a gold wire or a copper wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **832**, exposed by the openings **9939'** in the polymer layer **99** using a wirebonding process.

[0343] Referring to FIGS. **10**D and **10**E, before the patterned circuit layer **831** is formed, a polymer layer **95** can be optionally formed by a suitable process or processes, e.g., by

spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads **6390**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9539**, **9539'**, **9531**, **9532** and **9534** may be formed in the polymer layer **95**, exposing multiple contact pads **6390** exposed by the openings **539**, **539'**, **531**, **532** and **533** in the passivation layer **5**. After the polymer layer **95** is formed, the patterned circuit layer **831** can be formed on the polymer layer **95** and on the contact pads **6390** exposed by the openings **539**, **539'**, **531**, **532** and **533**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer **95** and on the contact pads **6390** exposed by the openings **9539**, **9539'**, **9531**, **9532** and **9534** in the polymer layer **95**.

[0344] Alternatively, referring to FIG. **10**F, the off-chip buffer **42**, such as off-chip driver of FIG. **11**A, **11**D or **11**E, off-chip receiver of FIG. **11**B or tri-state buffer of FIG. **11**C or **11**E, can be connected to the internal circuits **20** through the fine-line metal trace **638** under the passivation layer **5** but not through any trace or bus over the passivation layer **5**. There may be only one patterned circuit layer **831** including a portion serving as the previously described thick and wide metal trace **83***r*, over the passivation layer **5**. The position of the contact point **8310** of the previously described thick and wide metal trace **83***r* for being wirebonded thereto from a top perspective view is different from that of the contact pad exposed by the opening **539** in the passivation layer **5**. The process for forming the patterned circuit layer **831** can be referred to as that for forming the patterned circuit layer **831** shown in FIG. **10**B. The process for forming the polymer layer **99** can be referred to as that for forming the polymer layer **99** shown in FIG. **10**B.

[0345] Referring to FIG. **10**F, a gold wire pr a copper wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **831**, exposed by the openings **9939** in the polymer layer **99** using a wirebonding process.

[0346] As an alternate, referring to FIG. **10**F, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact point **8310** exposed by the opening **9939** in the polymer layer **99**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9939** in the polymer layer **99**. Thereafter, a gold wire or a copper wire can be bonded onto the electroless plated gold layer in the opening **9939** in the polymer layer **99** using a wirebonding process.

[0347] Referring to FIGS. **10**G-**10**I, a gold wire or a copper wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **831**, exposed by the openings **9939** in the polymer layer **99** using a wirebonding process.

[0348] As an alternate, referring to FIGS. **10**G-**10**I, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact point **8310** exposed by the opening **9939** in the polymer layer **99**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9939** in the polymer layer **99**. Thereafter, a gold wire can be bonded onto the electroless plated gold layer in the opening **9939** in the polymer layer **99** using a wirebonding process.

[0349] The circuitry shown in FIGS. **8**B-**8**F, **9**B-**9**B and **10**B-**10**I can be used in a flash memory chip, in a DRAM memory chip or in a SRAM memory chip. The I/O pad relocation using the redistribution layer **83***r* is particularly useful for the stacked packaging with flash, DRAM or SRAM memory chips. The I/O pads of a DRAM chip are usually designed roughly along the centerline of the chip, and cannot be used for stacked packages. The redistribution layer **83***r* relocates the center pad to the peripheral of the chip for the wirebonding in the stacked package. FIGS. **10**F and **10**G show specific examples, with a wire bonded on the contact point **8310** connected to the original pad **6390** exposed by the opening **539** in the passivation layer **5** via the thick and wide metal trace of bus **83***r*. In FIGS. **8**B, **9**B, **10**B-**10**G, in an application to a memory chip, an SRAM cell, or a flash memory cell, or a DRAM cell is connected to the input node Xi of the internal circuit **21**, such as sense amplifier, internal tri-state buffer **213** of FIG. **5**F, pass circuit **216** of FIG. **5**G, latch circuit **217** of FIG. **5**H, circuit of pass circuit **216** and internal driver **212** shown in FIG. **5**I, or circuit of latch circuit **217** and internal driver **212** shown in FIG. **5**J. The various detailed internal circuit **21** and methods connecting a memory cell to the internal circuit **21** can be referred to as shown in FIGS. **5**F-**5**J. Referring to FIGS. **8**B, **8**D-**8**F, **9**B-**9**D and **10**B-**10**I, an SRAM cell, or a flash cell or a DRAM cell is connected to external circuit (1) through sense amplifier **214** of FIGS. **5**F-**5**J; (2) through an internal tri-state buffer **213** of FIG. **5**F, a pass circuit **216** of FIG. **5**G, a latch circuit **217** of FIG. **5**H, a circuit of a pass circuit **216** and an internal driver **212** as shown in FIG. **5**I, or a circuit of a latch circuit **217** and an internal driver **212** as shown in FIG. **5**J; (3) through a first fine-line structure formed by a suitable process or processes, e.g., by stacked vias and metals **631**; (4) up through a first passivation opening **531**; (5) for **10**G, also through a first polymer opening **9531**; (6) through a fine-line metal **638** under the passivation layer **5** for FIG. **10**F; while through an over-passivation metal lines, traces or planes **83** in one or more metal layers over the passivation layer **5** for FIG. **10**G; (7) for FIG. **10**G, down through a second polymer opening **9539'**; (8) through a second passivation opening **539'**; (9) through a fine-line metal structure formed by a suitable process or processes, e.g., by stacked vias and metal pads **639'**, connected to the input of an off-chip buffer **42**, (10) through the output of the off-chip buffer **42** connected to an off-chip ESD circuit **43**, and to a stacked fine-line metal vias and metal pads **639**, (11) through an passivation opening **539**, (12) for **10**G, also through a third polymer opening **9539**; and (13) through an over-passivation redistribution metal lines or traces or planes **83***r*, (14) through over-passivation metal pad **8310** exposed by a polymer opening **9939**; (15) through a bonding wire **89'** on the contact point **8310** or a metal bump **89**.

[0350] Note that as in FIG. **10**G, there may be a polymer layer under or over the redistribution metal layer **83***r*. The redistribution metal lines, traces or planes **83***r* can be formed by a suitable process or processes, e.g., by a (electroplated or electroless plated) gold layer with thickness within a range between 1.5 μm and 30 μm, exemplary 2 μm and 10 μm; or by a (electroplated) copper layer with thickness within a range between 2 μm and 100 μm, exemplary 3 μm and 20 μm, a Ni cap layer (thickness between 0.5 μm and 5 μm) on the copper

layer and an assembly metal layer of Au or Pd, or Ru (thickness between 0.05 μm and 5 μm) on the Ni cap layer. A wirebonding is performed on the surface of the gold, palladium, platinum or ruthenium layer of the over-passivation metal pad **8310**.

[0351] Referring to FIGS. **8**B-**8**F, **9**B-**9**D, **10**B-**10**E and **10**G-**10**I, the shape of the openings **531**, **532**, **534** and **539'** in the passivation layer **5** from a top perspective view may be round, square, rectangular or polygon. If the openings **531**, **532**, **534**, **539** and **539'** are round, the openings **531**, **532**, **534**, **539** and **539'** may have a diameter of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **531**, **532**, **534**, **539** and **539'** are square, the openings **531**, **532**, **534**, **539** and **539'** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **531**, **532**, **534**, **539** and **539'** are rectangular, the openings **531**, **532**, **534**, **539** and **539'** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns, and a length of between 1 micron and 1 centimeter. If the openings **531**, **532**, **534**, **539** and **539'** are polygon having more than five sides, the openings **531**, **532**, **534**, **539** and **539'** have a largest diagonal length of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. Alternatively, the openings **531**, **532**, **534**, **539** and **539'** have a largest transverse dimension of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. In a case shown in FIGS. **10**C-**10**E, **10**G, **10**H and **10**I, the openings **531**, **532**, **534**, **539** and **539'** have a width of between 0.1 and 30 microns, with the lower portion of the openings **9531**, **9532**, **9534**, **9539** and **9539'** in the polymer layer **95** having a width of between 20 and 100 microns. The openings **9531**, **9532** and **9534** in the polymer layer **95** have lower portions having widths or transverse dimensions larger than those of the openings **531**, **532** and **534** in the passivation layer **5** aligned with the openings **9531**, **9532** and **9534**, respectively. The openings **9531**, **9532** and **9534** in the polymer layer **95** further expose the passivation layer **5** close to the openings **531**, **532** and **534**. The polymer layer **95** covers the peripheral region of the contact pad exposed by the openings **539** and **539'** in the passivation layer **5**, but the openings **9539** and **9539'** in the polymer layer **95** exposes the center region of the contact pad exposed by the openings **539** and **539'** in the passivation layer **5**. The widths or transverse dimensions of the openings **539** and **539'** in the passivation layer **5** are larger than those of the openings **9539** and **9539'**, respectively.

[0352] In FIGS. **8**A-**8**F, a dotted line **5** indicates the passivation layer, coarse traces indicate traces of an over-passivation scheme **102** formed over the passivation layer **5**, and fine traces indicate traces formed under the passivation layer **5**. In FIGS. **9**A-**9**D, coarse traces indicate the traces of the over-passivation scheme **102** formed over the passivation layer **5**, and fine traces indicate the traces formed under the passivation layer **5**. The over-passivation scheme **102** shown in FIG. **10**A includes the polymer layer **99**, the metal trace **83***r* provided by the patterned circuit layer **831**, and the metal bump **89**, and the opening **9939** in polymer layer **99** is over the contact point **8310** of the metal trace **83***r*, and the metal bump **89** is in the opening **9939**, on the contact point **8310** and on the polymer layer **99**. The over-passivation scheme **102** shown in FIG. **10**B includes the polymer layer **99**, the metal traces **83** and **83***r* provided by the patterned circuit layer **831**, and the metal bump **89**, and the opening **9939** in polymer layer **99** is over the contact point **8310** of the metal trace **83***r*, and the metal bump **89** is in the opening **9939**, on the contact point **8310** and on the polymer layer **99**. The over-passivation scheme **102** shown in FIG. **10**C includes the polymer layers **98** and **99**, the metal traces **83** and **83***r* provided by the patterned circuit layers **831** and **832**, and the metal bump **89**, and the opening **9939'** in polymer layer **99** is over the contact point **8320** of the metal trace **83***r*, and the metal bump **89** is in the opening **9939'**, on the contact point **8320** and on the polymer layer **99**. The over-passivation scheme **102** shown in FIG. **10**D includes the polymer layers **95** and **99**, the metal traces **83** and **83***r* provided by the patterned circuit layer **831**, and the metal bump **89**, and the openings **9539**, **9539'**, **9531**, **9532** and **9534** are in the polymer layer **95**, and the opening **9939** in polymer layer **99** is over the contact point **8320** of the metal trace **83***r*, and the metal bump **89** is in the opening **9939**, on the contact point **8320** and on the polymer layer **99**. The over-passivation scheme **102** shown in FIG. **10**E includes the polymer layers **95**, **98** and **99**, the metal traces **83** and **83***r* provided by the patterned circuit layers **831** and **832**, and the metal bump **89**, and the openings **9539**, **9539'**, **9531**, **9532** and **9534** are in the polymer layer **95**, and the openings **9831**, **9834** and **9839** in the polymer layer **98** are over the patterned circuit layer **831**, and the opening **9939'** in polymer layer **99** is over the contact point **8320** of the metal trace **83***r*, and the metal bump **89** is in the opening **9939'**, on the contact point **8320** and on the polymer layer **99**. The over-passivation scheme **102** shown in FIG. **10**F includes the polymer layer **99** and the metal trace **83***r* provided by the patterned circuit layer **831**, and the opening **9939** in the polymer layer **99** is over the contact point **8310** of the metal trace **83***r* and exposes it. The over-passivation scheme **102** shown in FIGS. **10**G-**10**I includes the polymer layers **95** and **99** and the metal traces **83** and **83***r* provided by the patterned circuit layer **831**, and the openings **9539**, **9539'**, **9531**, **9532** and **9534** are in the polymer layer **95**, and the opening **9939** in the polymer layer **99** is over the contact point **8310** of the metal trace **83***r* and exposes it.

Fourth Embodiment: Power/Ground Buses Design Architecture

[0353] In the first embodiment of present disclosure described previously, an external power supply Vdd is provided to the voltage regulator or converter circuit **41**, and the voltage regulator or converter circuit **41** outputs a power supply Vcc to the internal circuits **20**. Alternatively, the external power supply Vdd can be input from an external circuit to the internal circuits **20**, including **21**, **22**, **23** and **24**, with an ESD protection circuit **44** required to prevent the voltage or current surge from damaging the internal circuits **20**. The ESD circuit **44** is connected in parallel with the internal circuits **21**, **22**, **23** and **24**. In the first embodiment in FIGS. **1**B, **1**C, **2**B, **2**C, **3**B, **3**C and **3**D, an ESD circuit can be also added and connected in parallel with the voltage regulator or converter circuit **41**, and with the internal circuits **21**, **22**, **23** and **24**. For example, the circuit shown in FIG. **1**D contains the circuit of FIG. **1**C in addition with an ESD circuit **44**. The ESD circuit **44** includes a power node Dp connected to a thick and wide power bus or plane **81**P, delivering an external power voltage Vdd, and a ground node Dg connected to a thick and wide ground bus or plane **82**. The thick and wide power bus or plane **81**P connects the power node Dp of the ESD circuit **44** and the power node of the voltage regulator or converter circuit **41**. The thick and wide ground bus or plane

82 connects the ground node Dg of the ESD circuit **44** and the ground node Rs of the voltage regulator or converter circuit **41**. The ESD circuit **44** in the circuitry of FIG. **1**D may be a reverse biased diode **4333**, as shown in FIG. **12**E, having an anode connected to the thick and wide ground bus or plane **82** and a cathode connected to the thick and wide power bus or plane **81**P. An element in FIG. **1**D can be referred to as the element in FIG. **1**C indicated by a reference number identical to the element in FIG. **1**D.

[0354] FIG. **12**B shows a circuit diagram including a thick and wide power bus or plane **81**P over the passivation layer **5**, connecting an ESD circuit **44** and internal circuits **20**. FIG. **13**B shows a top view realizing the circuit diagram of FIG. **12**B, and the bold lines shown in FIG. **13**B means a thick and wide metal trace or bus over a passivation layer, and the fine lines shown in FIG. **13**B means a fine metal trace under a passivation layer. FIG. **14**B shows a cross-sectional view realizing the circuit diagram of FIG. **12**B. In FIG. **12**B, an external power supply voltage Vdd is input at a node Ep and distributed to the Vdd nodes, power nodes, Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24** through a thick and wide power bus or plane **81**P over the passivation layer **5**, through passivation openings **511**, **512** and **514**, and through power fine-line metal traces **611**, **612** and **614** under the passivation layer **5**. A power node Dp of an ESD circuit **44** is connected to a thick and wide metal trace, bus or plane **81**P, power bus, through a fine-line metal trace or bus **649**, and through an opening **549** in the passivation layer **5**. The thick and wide power bus **81**P can be connected to the power nodes Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24** that may include a NOR gate, NAND gate, AND gate, OR gate, operational amplifier, adder, multiplexer, diplexer, multiplier, A/D converter, D/A converter, CMOS device, bi-polar CMOS device, bipolar circuit, SRAM cell, DRAM cell, non-volatile memory cell, flash memory cell, EPROM cell, ROM cell, magnetic RAM (MRAM) or sense amplifier. The above mentioned power bus **81**P shown in FIG. **12**B, over the passivation layer **5**, can be connected to the power nodes of the internal circuits **20** or other circuits in the previously described four embodiments provided with access to a power voltage Vdd. The ESD circuit **44** in the circuitry of FIG. **12**B may be a reverse biased diode **4333**, as shown in FIG. **12**E, having an anode connected to ground and a cathode connected to the thick and wide power bus or plane **81**P.

[0355] In FIG. **14**B, there is only one patterned circuit layer **811**, including a portion serving as the previously described thick and wide metal trace **81**P, power bus or plane, over the passivation layer **5**. The patterned circuit layer **811** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8112** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8111**.

[0356] Referring to FIG. **14**B, regards to the process for forming the patterned circuit layer **811**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on a silicon-nitride layer of the passivation layer **5** and on contact pads **6490**, principally made of aluminum or copper, exposed by multiple openings **549**, **511**, **512** and **514** in the passivation layer **5**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8112** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8112** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8112** is removed using a wet-etching process or using a dry-etching process.

[0357] After the patterned circuit layer **811** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **811** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9949** may be formed in the polymer layer **99**, exposing a contact pad **8110** of the patterned circuit layer **811**.

[0358] Referring to FIG. **14**B, for forming a metal bump over the contact pad **8110**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8110** exposed by the opening **9949**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on

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the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 0.5 and 10 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, and then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, having a thickness between 60 and 200 micrometers on the electroplated nickel layer in the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the metal bump can be reflowed to be shaped like a ball for a flip-chip assembly. The metal bump can be connected to a printed circuit board, ceramic substrate or another semiconductor chip.

[0359] Referring to FIG. **14**B, for forming another kind of metal bump over the contact pad **8110**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8110** exposed by the opening **9949**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a gold layer having a thickness between 6 and 25 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. The metal bump can be connected to a flexible substrate by a tape-automated bonding (TAB) process, or a glass substrate via anisotropic conductive film or paste (ACF or ACP).

[0360] Alternatively, referring to FIG. **14**B, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact pad **8110** exposed by the opening **9949**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9949** in the polymer layer **99**. Thereafter, a gold wire can be bonded onto the electroless plated gold layer in the opening **9949** in the polymer layer **99** using a wirebonding process.

[0361] Alternatively, referring to FIG. **14**B, a gold wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **811**, exposed by the openings **9949** in the polymer layer **99** using a wirebonding process.

[0362] Referring to FIG. **14**D, before the patterned circuit layer **811** is formed, a polymer layer **95** can be optionally formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads **6490**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings **9549**, **9511**, **9512** and **9514** may be formed in the polymer layer **95**, exposing multiple contact pads **6490** exposed by the openings **549**, **511**, **512** and **514** in the passivation layer **5**. After the polymer layer **95** is formed, the patterned circuit layer **811** can be formed on the polymer layer **95** and on the contact pads **6490** exposed by the openings **549**, **511**, **512** and **514**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer **95** and on the contact pads **6490** exposed by the openings **9549**, **9511**, **9512** and **9514** in the polymer layer **95**.

[0363] FIG. **12**C shows, in addition to the power Vdd connection in FIG. **12**B, a ground Vss connection. FIG. **13**C shows a top view realizing the circuit diagram of FIG. **12**C, and the bold lines shown in FIG. **13**C means a thick and wide metal trace or bus over a passivation layer, and the fine lines shown in FIG. **13**C means a fine metal trace under a passivation layer. FIG. **14**C shows a cross-sectional view realizing the circuit diagram of FIG. **12**C. In FIG. **12**C, the external ground Vss is input at a node Eg and provided to the Vss nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through a thick and wide metal trace, bus or plane **82**, ground bus or plane, over the passivation layer **5**, through openings **521**, **522** and **524** in the passivation layer **5**, and through fine-line metal traces **621**, **622** and **624** under the passivation layer **5**. The thick and wide ground bus or plane **82** is connected to a Vss node Dg of the ESD circuit **44** through an opening **549'** in the passivation layer **5** and through a fine-line ground metal bus **649'** under the passivation layer **5**. The above mentioned power bus **81**P shown in FIG. **12**C, over the passivation layer **5**, can be connected to the power nodes of the internal circuits **20** or other circuits in the previously described four embodiments provided with access to a power voltage Vdd. The above mentioned ground bus **82** shown in FIG. **12**C, over the passivation layer **5**, can be connected to the ground nodes of the internal circuits **20** or other circuits in the previously described four embodiments provided with access to a ground voltage Vss. The ESD circuit **44** in the circuitry of FIG. **12**C may be a reverse biased diode **4333**, as shown in FIG. **12**E, having an anode connected to the thick and wide ground bus or plane **82** and a cathode connected to the thick and wide power bus or plane **81**P.

[0364] Referring to FIG. **14**C, there may be multiple patterned circuit layers **821** and **812**, including the previously described ground bus or plane **82** and the previously described power bus or plane **81**P over the ground bus or plane **82**, over the passivation layer **5**. The process for forming the patterned circuit layer **821** on the passivation layer **5** and on the contact pads **6490'** exposed by the openings **549'**, **521**, **522** and **524** can be referred to as the process for forming the patterned circuit layer **811** shown in FIG. **14**B on the passivation layer **5** and on the contact pads **6490** exposed by

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the openings **549**, **511**, **512** and **514**. The patterned circuit layer **821** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8212** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8211**. The patterned circuit layer **812** may contain an adhesion/barrier layer, a seed layer on the adhesion/barrier layer, and an electroplated metal layer **8122** on the seed layer, the adhesion/barrier layer and the seed layer composing the bottom layer **8121**.

[0365] Referring to FIG. **14**C, after the patterned circuit layer **821** is formed, a polymer layer **98** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **821** and on the nitride layer of the passivation layer **5**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9849'** may be formed in the polymer layer **98**, exposing a contact pad of the patterned circuit layer **821**.

[0366] Referring to FIG. **14**C, regards to the process for forming the patterned circuit layer **812**, the adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **98** and on the contact pad of the patterned circuit layer **821** exposed by the opening **9849'** in the polymer layer **98**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material or by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal layer **8122** may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer and then electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, by electroplating a copper layer having a thickness between 2 and 30 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer and then electroplating a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers on the electroplated nickel layer in the openings in the photoresist layer, or by electroplating a gold layer having a thickness between 2 and 30 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal layer **8122** is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal layer **8122** is removed using a wet-etching process or using a dry-etching process.

[0367] After the patterned circuit layer **812** is formed, a polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the patterned circuit layer **812** and on the polymer layer **98**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, an opening **9949'** may be formed in the polymer layer **99**, exposing a contact pad **8120** of the patterned circuit layer **812**.

[0368] Referring to FIG. **14**C, for forming a metal bump over the contact pad **8120**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, sputtering a chromium-containing layer, such as chromium layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8120** exposed by the opening **9949'**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a copper layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a copper layer having a thickness between 0.5 and 10 micrometers on the copper layer serving as the seed layer, exposed by the openings in the photoresist layer, electroplating a nickel layer having a thickness between 0.5 and 10 micrometers on the electroplated copper layer in the openings in the photoresist layer, and then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, having a thickness between 60 and 200 micrometers on the electroplated nickel layer in the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the metal bump can be reflowed to be shaped like a ball. The metal bump can be connected to a printed circuit board, ceramic substrate or another semiconductor chip.

[0369] Referring to FIG. **14**C, for forming another kind of metal bump over the contact pad **8120**, an adhesion/barrier layer may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or a titanium-tungsten-alloy layer, having a thickness between 1000 and 6000 angstroms, or sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness between 1000 and 6000 angstroms, on the polymer layer **99** and on the contact pad **8120** exposed

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by the opening **9949'**. Thereafter, the seed layer may be formed by a suitable process or processes, e.g., by sputtering a gold layer having a thickness between 200 and 3000 angstroms on the adhesion/barrier layer of any previously described material. Thereafter, a photoresist layer may be formed on the seed layer, multiple openings in the photoresist layer exposing the seed layer. Thereafter, the metal bump may be formed by a suitable process or processes, e.g., by electroplating a gold layer having a thickness between 6 and 25 micrometers on the gold layer serving as the seed layer, exposed by the openings in the photoresist layer. Thereafter, the photoresist layer may be removed. Thereafter, the seed layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. Thereafter, the adhesion/barrier layer not under the metal bump is removed using a wet-etching process or using a dry-etching process. The metal bump can be connected to a flexible substrate by a tape-automated bonding (TAB) process, or a glass substrate via anisotropic conductive film or paste (ACF or ACP).

[0370] Alternatively, referring to FIG. **14**C, a nickel layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the contact pad **8120** exposed by the opening **9949'** in layer polymer layer **99**, and a gold layer, platinum layer, palladium layer or ruthenium layer having a thickness between 0.05 and 2 micrometers can be electroless plated on the electroless plated nickel layer in the opening **9949'** in the polymer layer **99**. Thereafter, a gold wire can be bonded onto the electroless plated gold layer in the opening **9949'** in the polymer layer **99** using a wirebonding process.

[0371] Alternatively, referring to FIG. **14**C, a gold wire can be bonded onto a gold layer, platinum layer, palladium layer or ruthenium layer of the patterned circuit layer **812**, exposed by the openings **9949'** in the polymer layer **99** using a wirebonding process.

[0372] Alternatively, before the patterned circuit layer **821** is formed, a polymer layer can be optionally formed by a suitable process or processes, e.g., by spin-on coating a negative photosensitive polyimide layer, such as ester type, on the nitride layer of the passivation layer **5** and on the contact pads **6490'**, exposing the spin-on coated photosensitive polyimide layer, developing the exposed polyimide layer and then curing the developed polyimide layer at the temperature between 265 and 285° C. for a time between 30 and 240 minutes in a nitrogen or oxygen-free ambient. Accordingly, multiple openings may be formed in the polymer layer, exposing multiple contact pads **6490'** exposed by the openings **549'**, **521**, **522** and **524** in the passivation layer **5**. After the polymer layer is formed, the patterned circuit layer **821** can be formed on the polymer layer and on the contact pads **6490'** exposed by the openings **549'**, **521**, **522** and **524**. The adhesion/barrier layer of any previously described material may be sputtered on the polymer layer and on the contact pads **6490'** exposed by the openings in the polymer layer.

[0373] Alternatively, the previously described power bus or plane **81**P and the previously described ground bus or plane **82** can be connected to two ESD circuits **44** and **45**, as shown in FIG. **12**D. The previously described power bus or plane **81**P may connect the power nodes Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24** and the power nodes Dp and Dp' of the ESD circuits **44** and **45**. The previously described ground bus or plane **82** may connect the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** and the ground nodes Dg and Dg' of the ESD circuits **44** and **45**. The above mentioned power bus **81**P shown in FIG. **12**D, over the passivation layer **5**, can be connected to the power nodes of the internal circuits **20** or other circuits in the previously described four embodiments provided with access to a power voltage Vdd. The above mentioned ground bus **82** shown in FIG. **12**D, over the passivation layer **5**, can be connected to the ground nodes of the internal circuits **20** or other circuits in the previously described four embodiments provided with access to a ground voltage Vss. Each of the ESD circuit **44** and **45** in the circuitry of FIG. **12**D may be a reverse biased diode **4333**, as shown in FIG. **12**E, having an anode connected to the thick and wide ground bus or plane **82** and a cathode connected to the thick and wide power bus or plane **81**P.

[0374] Referring to FIGS. **12**B-**12**D, **13**B, **13**C and **14**B-**14**D, the shape of the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** in the passivation layer **5** from a top perspective view may be round, square, rectangular or polygon. If the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** are round, the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** may have a diameter of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** are square, the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. If the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** are rectangular, the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** may have a width of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns, and a length of between 1 micron and 1 centimeter. If the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** are polygon having more than five sides, the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** have a largest diagonal length of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. Alternatively, the openings **511**, **512**, **514**, **521**, **522**, **524**, **549** and **549'** have a largest transverse dimension of between 0.1 and 200 microns, between 1 and 100 microns, or, preferably, between 0.1 and 30 microns. In a case shown in FIG. **14**D, the openings **511**, **512**, **514** and **549** have a width of between 0.1 and 30 microns, with the lower portion of the openings **9511**, **9512**, **9514** and **9549** in the polymer layer **95** having a width of between 20 and 100 microns. The openings **9511**, **9512** and **9514** in the polymer layer **95** have lower portions having widths or transverse dimensions larger than those of the openings **511**, **512** and **514** in the passivation layer **5** aligned with the openings **9511**, **9512** and **9514**, respectively. The openings **9511**, **9512** and **9514** in the polymer layer **95** further expose the passivation layer **5** close to the openings **511**, **512** and **514**. The polymer layer **95** covers the peripheral region of the contact pad exposed by the opening **549** in the passivation layer **5**, but the opening **9549** in the polymer layer **95** exposes the center region of the contact pad exposed by the openings **549** in the passivation layer **5**. The width or transverse dimension of the opening **549** in the passivation layer **5** is larger than that of the opening **9549**.

[0375] In FIGS. **12**B-**12**D, a dotted line **5** indicates the passivation layer, coarse traces indicate traces of an over-passivation scheme **102** formed over the passivation layer **5**, and fine traces indicate traces formed under the passivation layer **5**. In FIGS. **13**B and **13**C, coarse traces indicate the traces of the over-passivation scheme **102** formed over the passivation layer **5**, and fine traces indicate the traces formed under the passivation layer **5**. The over-passivation scheme

102 shown in FIG. **14**B includes the polymer layer **99** and the metal trace **81**P provided by the patterned circuit layer **811**, and the opening **9949** in the polymer layer **99** is over the contact point **8110** of the metal trace **81**P and exposes it. The over-passivation scheme **102** shown in FIG. **14**C includes the polymer layers **98** and **99**, the metal trace **81**P provided by the patterned circuit layer **812**, and the, metal trace **82** provided by the patterned circuit layer **821**, and the opening **9849'** in the polymer layer **98** is over the metal trace **82**, and the opening **9949'** in the polymer layer **99** is over the contact point **8120** of the patterned circuit layer **812** and exposes it. The over-passivation scheme **102** shown in FIG. **14**D includes the polymer layers **95** and **99** and the metal trace **81**P provided by the patterned circuit layer **811**, and the openings **9549**, **9511**, **9512** and **9514** are in the polymer layer **95**, and the opening **9949** in the polymer layer **99** is over the contact point **8110** of the metal trace **81**P and exposes it.

Formation of an Over-Passivation Scheme

[0376] A main characteristics of the over-passivation schemes in exemplary embodiments of this disclosure are thick metal layers each having a thickness larger than 1 micrometer, such as between 2 and 200 micrometers, and preferably between 2 and 30 micrometers, and thick dielectric layers each having a thickness larger than 2 micrometers, such as between 2 and 300 micrometers, and preferably between 2 and 30 micrometers.

[0377] FIGS. **15**C-**15**H show an embossing process to fabricate a patterned circuit layer **801** over the passivation layer **5** and on the polymer layer **95**, which can be applied to all embodiments in this disclosure. FIGS. **15**I-**15**J show an embossing process to fabricate a patterned circuit layer **802** on the patterned circuit layer **801** and on the polymer layer **98**, which can be applied to all embodiments in this disclosure. FIGS. **15**C-**15**G and FIGS. **16**A-**16**K show a double embossing process to fabricate one or more patterned circuit layers **801** and **802** over the passivation layer **5**, which can be applied to all embodiments in this disclosure. A polymer layer **95** may be provided under the patterned circuit layer **801** and over the passivation layer **5**. A polymer layer **98** may provided between the patterned circuit layers **801** and **802** and over the passivation layer **5**. A polymer layer **19** may be provided over the patterned circuit layer **802** and over the passivation layer **5**. FIGS. **15**A-**15**M and FIGS. **16**A-**16**M are based on the structure of FIG. **10**E in the third embodiment, and are used as examples to illustrate methods for forming the over-passivation scheme for all embodiments in this disclosure. In other words, the methods described and the specification specified in the following paragraphs can be applied to all metal traces, buses or planes **81**, **81**P, **82**, **83**, **83'**and **85** and all metal layers **811**, **821**, **831**, **812** and **832** in this disclosure.

[0378] FIG. **15**A shows a starting material for the over-passivation process. The over-passivation process starts on a wafer **10** finalized to be cut into chips after the over-passivation scheme of the top post-passivation technology is formed on the wafer **10**.

[0379] The semiconductor wafer **10** includes elements, as follows:

[0380] Reference number of **1** indicates a substrate, usually a silicon substrate, having a thickness between 600 and 1000 micrometers, between 50 micrometers and 1 millimeter or between 75 and 250 micrometers. The silicon substrate can be an intrinsic, a p-type, or an n-type silicon substrate. For a high performance chip, a SiGe or Silicon-On-Insulator (SOI) substrate can be used. A SiGe substrate includes an epitaxial layer on the surface of a silicon substrate. An SOI substrate includes an insulating layer (exemplary silicon oxide) on a silicon substrate, and a Si or SiGe epitaxial layer formed over the insulating layer.

[0381] Reference number of **2** indicates a device layer, usually a semiconductor device, in and/or on the substrate **1**. The semiconductor device includes an MOS transistor **2'**, either an n-MOS or a p-MOS transistor. The MOS transistor includes a gate (usually a poly-silicon, a tungsten poylcide, a tungsten silicide, titanium silicide, cobalt silicide, or a salicide gate), a source, and a drain. Other devices are bipolar transistors, DMOS (Diffused MOS), LDMOS (Lateral Diffused MOS), CCD (Charged-Coupled Device), CMOS sensors, photo-sensitive diodes, resistors (formed by the poly-silicon layer or the diffusion area in the silicon substrate). The devices form various circuits, such as CMOS circuits, NMOS circuits, PMOS circuits, BiCMOS circuits, CMOS sensor circuits, DMOS power circuits, or LDMOS circuits. The layer includes the internal circuits **20** (including **21**, **22**, **23** and **24**) in all embodiments; the voltage regulator or converter circuit **41** in the first embodiment; the off-chip circuit **40** (including **42** and **43**) in the third embodiment, and the ESD circuit **44** in the fourth embodiment.

[0382] Reference number of **6** indicates a fine-line scheme, including fine-line metal layers **60** and fine-line via plugs **60'** in vias **30'** of fine-line dielectric layers **30**. The fine-line scheme **6** includes fine-line metal traces in all embodiments of this disclosure: (1) **611**, **612**, **614**, **619**, **619'**, **621**, **622**, **624** and **629** of the first embodiment; (2) **631**, **632** and **634** of the second embodiment; (3) **631**, **632**, **634**, **639**, **639'**, **6391**, **6391'**, **6311**, **6321** and **6341** of the third embodiment; (4) **611**, **612**, **614**, **649**, **621**, **622**, **624** and **649'** of the fourth embodiment. The fine-line metal layers **60** can be aluminum or copper layers, or more specifically, sputtered aluminum layers or damascene copper layers. The fine-line metal layers **60** can be (1) all fine-line metal layers are aluminum layers, (2) all fine-line metal layers are copper layers, (3) the bottom layers are aluminum layers and the top layers are copper layer, or (4) the bottom layers are copper layers and the top layers are aluminum layers. The fine-line metal layers **60** may have a thickness between 0.05 and 2 micrometers, and preferably between 0.2 and 1 micrometers, with horizontal design rules (the width) of lines or traces smaller than 1 micrometer, such as between 0.05 and 0.95 micrometers, or larger than 20 nanometers, such as between 20 nanometers and 15 micrometers, and preferably between 20 nanometers and 2 micrometers. The aluminum layer is usually formed by a suitable process or processes, e.g., by a physical vapor deposition (PVD) method, such as the sputtering method, and then patterned by depositing a photoresist layer with thickness between 0.1 and 4 micrometers, and preferably 0.3 and 2 micrometers, followed by a wet or dry etching, exemplary dry plasma etch (usually containing fluorine plasma). As an option, an adhesion/barrier (Ti, TiW, TiN or a composit layer of above metals) may be added under the aluminum layer, and/or an anti-reflection layer (TiN) may be also added over the aluminum layer. The vias **30'** are optionally filled with blanketed CVD tungsten deposition, followed by a chemical mechanical polishing (CMP) of the tungsten metal layer to form via plugs **60'**. The copper layer is usually formed by a suitable process or processes, e.g., by a damascene process including an electroplating process as follows: (1) depositing a copper diffusion barrier layer (such as oxynitride or nitride

layer of thickness between 0.05 and 0.25 μm); (2) depositing a dielectric layer **30** of a thickness between 0.1 and 2.5 μm, exemplary between 0.3 and 1.5 μm by PECVD, spin-on coating, and/or High-Density Plasma (HDP) CVD methods; (3) patterning the dielectric layer **30** by depositing a photoresist layer with a thickness between 0.1 and 4 μm, and preferably between 0.3 and 2 μm, then exposing and developing the photoresist layer to form openings and/or trenches, and then stripping the photoresist layer; (4) depositing an adhesion/barrier layer and an electroplating seed layer by sputtering and/or CVD methods. The adhesion/barrier layer includes Ta, TaN, TiN, Ti or TiW or a composite layer formed by a suitable process or processes, e.g., by above materials. The electroplating seed layer, formed on the adhesion/barrier layer, is usually a copper layer formed by a suitable process or processes, e.g., by sputtering Cu or CVD copper or a CVD Cu followed by a sputtering Cu; (5) electroplating a copper layer over the electroplating seed layer to a thickness smaller than 1 micrometer, such as between 0.05 and 1 micrometers, and preferably between 0.2 and 1 micrometers; (6) removing the electroplated copper layer, the electroplating seed layer and the adhesion/barrier layer not in the openings or trenches of the dielectric layer **30** by polishing (exemplary chemical mechanical polishing, CMP) the wafer until the dielectric layer underlying the adhesion/barrier layer exposed. Only the metals in the openings or trenches remain after CMP; and the remained metals are used as metal conductors (lines, traces and/or planes) or via plugs **60'** connecting two adjacent metal layers **60**. As another alternative, a double-damascene process is used to form metal via plugs and metal traces, lines, or planes simultaneously with one electroplating process, one CMP process. Two photolithography processes, and two dielectric depositing processes are applied in the double-damascene process. The double-damascene process adds more process steps of deposing and patterning another layer of dielectrics between step (3) of patterning a dielectric layer and step (4) of depositing the metal layer in the above single damascene process. The dielectric layer **30** is formed by a suitable process or processes, e.g., by CVD (Chemical Vapor Deposition), PECVD (Plasma-Enhanced CVD), High-Density-Plasma (HDP) CVD, or a spin-on method. The materials of dielectric layers **30** include layers of silicon oxide, silicon nitride, silicon oxynitride, PECVD TEOS, Spin-On Glass (SOG, silicate-based or siloxane-based), Fluorinated Silicate Glass (FSG), or a low-K dielectric material such as Black Diamond (generated by machines of Applied Materials, Inc.), or ULK CORAL (generated by machines of Novellus Inc.), or SiLK (of IBM Corp.) low k dielectrics. The PECVD silicon oxide or PECVD TEOS or HDP oxide has a dielectric constant K between 3.5 and 4.5; the PECVD FSG or HDP FSG has a K value between 3.0 and 3.5, and the low K dielectric material has a K value between 1.5 and 3.0. The low K dielectric material, such as Black Diamond, is porous, and includes hydrogen and carbon in addition to silicon and oxygen, the formula is $H_wC_xSi_yO_z$. The fine-line dielectric layers **30** usually include inorganic materials. The dielectric layers **30** may have a thickness between 0.05 and 2 micrometers. The vias **30'** in the dielectric layer **30** is formed by a suitable process or processes, e.g., by wet and/or dry etching with photoresist patterning, exemplary dry etching. The dry etch species include fluorine plasma.

[0383] Reference number of **5** indicates a passivation layer. The passivation layer **5** plays a very important role in this disclosure. The passivation layer **5** is an insulating, protective layer that prevents mechanical and chemical damage during assembly and packaging. In addition to preventing mechanical scratch, it prevents the penetration of mobile ions, such as sodium, and transition metal, such as gold or copper, into the underlying IC devices. It also protects the underlying devices and interconnection (metals and dielectrics) from moisture penetration or other containments. The passivation layer **5** can be formed by a suitable process or processes, e.g., by a chemical vapor deposition (CVD) method, and typically has a thickness larger than 0.2 micrometers, such as between 0.3 and 1.5 micrometers or between 0.4 and 0.8 micrometers.

[0384] The passivation layer **5** can be composed of one or more inorganic layers. For example, the passivation layer **5** can be a composite layer of an oxide layer, such as silicon-oxide layer or silicon-oxycarbide (SiOC) layer, having a thickness smaller than 1.5 micrometers, such as between 0.1 and 1 micrometers, and preferably between 0.3 and 0.7 micrometers, and a nitride layer, such as silicon-nitride layer, silicon-oxynitride layer or silicon-carbon-nitride (SiCN) layer, having a thickness smaller than 1.5 micrometers, such as between 0.25 and 1.2 micrometers, and preferably between 0.35 and 1 micrometers, on the oxide layer. Alternatively, the passivation layer **5** can be a single layer of silicon nitride, silicon oxynitride or silicon carbon nitride (SiCN) having a thickness smaller than 1.5 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers. In a exemplary case, the passivation layer **5** includes a topmost inorganic layer of the semiconductor wafer **10**, and the topmost inorganic layer of the semiconductor wafer **10** can be a silicon-nitride layer having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers, or a silicon-oxide layer having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers. Alternatively, the passivation layer **5** can be a composite layer of an oxynitride layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.35 micrometers, and preferably between 0.1 and 0.2 micrometers, a first oxide layer with a thickness smaller than 1.2 micrometers, such as between 0.2 and 1.2 micrometers, and preferably between 0.3 and 0.6 micrometers, on the oxynitride layer, a nitride layer, such as silicon-nitride layer, with a thickness smaller than 1.2 micrometers, such as between 0.2 and 1.2 micrometers, and preferably between 0.3 and 0.5 micrometers, on the first oxide layer, and a second oxide layer with a thickness smaller than 1.2 micrometers, such as between 0.2 and 1.2 micrometers, and preferably between 0.3 and 0.6 micrometers, on the nitride layer. The first and second oxide layers can be PECVD silicon oxide, PETEOS oxide or high-density plasma (HDP) oxide.

[0385] The above description and specification for the substrate **1**, the device layer **2**, the fine-line metal scheme **6**, the dielectric layers **30** and the passivation layer **5** can be applied to all embodiments in this disclosure.

[0386] Openings **50** are formed in the passivation layer **5** by an etching process, such as a wet etching process or a dry etching process. The specification of the openings **50** and the process of forming the same can be applied to openings **511**, **512**, **514**, **519**, **519'**, **521**, **522**, **524**, **529**, **531**, **532**, **534**, **534'**, **531'**, **532'**, **539**, **539'**, **549**, **549'**, **559** and **559'** in this disclosure. The width of the opening **50** can be larger than 0.1 micrometers, such as between 0.1 and 200 micrometers, between 1 and 100 micrometers, between 0.5 and 30 micrometers or between 5 and 30 micrometers. The shape of the opening **50** from a top view may be a circle, and the

diameter of the circle-shaped opening **50** may be larger than 0.1 micrometers, such as between 0.1 and 30 micrometers or between 30 and 200 micrometers. Alternatively, the shape of the opening **50** from a top view may be a square, and the width of the square-shaped opening **50** may be larger than 0.1 micrometers, such as between 0.1 and 30 micrometers or between 30 and 200 micrometers. Alternatively, the shape of the opening **50** from a top view may be a polygon, such as hexagon or octagon, and the polygon-shaped opening **50** may have a width larger than 0.1 micrometers, such as between 0.1 and 30 micrometers or between 30 and 200 micrometers. Alternatively, the shape of the opening **50** from a top view may be a rectangle, and the rectangle-shaped opening **50** may have a shorter width larger than 0.1 micrometers, such as between 0.1 and 30 micrometers or between 30 and 200 micrometers. The width of the openings **531**, **532**, **534**, **531'**, **532'**, **534'**, **511**, **512** and **514** in the passivation layer **5** for the internal circuits **20** (including **21**, **22**, **23** and **24**) may be larger than 0.1 micrometers, such as between 0.1 and 100 micrometers, and preferably between 0.1 and 30 micrometers. The openings **519**, **519'** and **529** for the voltage regulator or converter circuit **41**, the openings **539** and **539'** for the off-chip buffer **42** and the off-chip ESD circuit **43**, and the openings **549**, **549'**, **559** and **559'** for the ESD circuit **44** may have a width larger than those of the openings **531**, **532**, **534**, **511**, **512** and **514**, in a range between 1 and 150 micrometers, and preferably between 5 and 100 micrometers. Alternatively, the openings **519**, **519'** and **529** for the voltage regulator or converter circuit **41**, the openings **539** and **539'** for the off-chip buffer **42** and the off-chip ESD circuit **43**, and the openings **549**, **549'**, **559** and **559'** for the ESD circuit **44** may have a width larger than those of the openings **531**, **532** and **534**, in a range between 0.1 and 30 micrometers. The openings **50** in the passivation layer **5** are over multiple regions of multiple metal pads or traces **600** of the fine-line metal layers **60** and expose them, and the regions of the metal pads or traces **600** are at bottoms of the openings **50**. The metal pads or traces **600** may include aluminum or electroplated copper.

[0387] The wafer **10** can be fabricated using different generations of IC process technologies, such as 1 μm, 0.8 μm, 0.6 μm, 0.5 μm, 0.35 μm, 0.25 μM, 0.18 μm, 0.25 μm, 0.13 μm, 90 nm, 65 nm, 45 nm, 35 nm or 25 nm technologies, defined by the gate length or effective channel length of the MOS transistors **2'**. The wafer **10** can be processed using photolithography process. The photolithography process can include coating, exposing and developing the photoresist. The photoresist used to process the wafer **10** has a thickness between 0.1 and 4 micrometers. A stepper or a scanner, e.g., a 5× stepper or scanner) can be used to expose the photoresist. The 5× means that the dimension on a photo mask (usual made of quartz) is reduced on the wafer when light beam is projected from the photo mask onto the wafer, and the dimension of a feature on the photo mask is 5 times of the dimension on the wafer. The scanner is used in advanced generations of IC process technologies, and is usually with 4× dimension reduction to improve the resolution. The wavelength of the light beam used in the stepper or the scanner can be 436 nm (g-line), 365 nm (i-line), 248 nm (Deep Ultraviolet, DUV), 193 nm (DUV), or 157 nm (DUV), or 13.5 nm (Extreme UV, EUV). The high-index immersion photolithography is also used to achieve fine-line features in the wafer **10**.

[0388] The wafer **10** is preferably processed in a clean room with Class **10** or better, for example Class **1**. A Class **10** clean room allows maximum number of particles per cubic foot: 1 larger than 1 μm, 10 larger than 0.5 μm, 30 larger than 0.3 μm, 75 larger than 0.2 μm, 350 larger than 0.1 μm, while a Class **1** clean room allows maximum number of particles per cubic foot: 1 larger than 0.5 μm, 3 larger than 0.3 μm, 7 larger than 0.2 μm, 35 larger than 0.1 μm.

[0389] When copper is used as the fine-line metal layers **60**, and exposed by the openings **50** in the passivation layer **5**, a metal cap **66**, including **661**, **662**, **664**, **669** and **669'**, is preferably used to protect the exposed copper pad or trace from corrosion as shown in FIG. **15**B. The metal cap **66** having a thickness between 0.4 and 3 micrometers includes an aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer), a gold layer, a Ti layer, a TiW layer, a Ta layer, a TaN layer, or a Ni layer. If the metal cap **66** is an aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer), a barrier layer having a thickness between 0.01 and 0.7 micrometers is formed between the aluminum cap **66** and the copper pad or trace, and the barrier layer includes Ti, TiW, TiN, Ta, TaN, Cr or Ni. For example, a barrier layer having a thickness between 0.01 and 0.7 micrometers can be formed on the copper pad or trace exposed by the opening **50**, and an aluminum-containing layer having a thickness between 0.4 and 3 micrometers is formed on the barrier layer, and the barrier layer may be made of titanium, a titanium-tungsten alloy, titanium nitride, tantalum, tantalum nitride, chromium or alloy of refractory metal, and the aluminum-containing layer may be an aluminum layer, an aluminum-copper alloy layer or an Al—Si—Cu alloy layer. The wafer or chip with metal caps **66** can be used as options in all embodiments in this disclosure.

[0390] FIGS. **15**C-**15**K show process steps of fabricating an over-passivation scheme **102** over the wafer **10** shown in FIG. **15**A or FIG. **15**B. The process steps shown in FIGS. **15**C-**15**K are used to form the structure shown in FIG. **10**E, for example, with two layers of over-passivation metals, and with complete design architecture for interconnecting the internal circuits **20** and off-chip circuits **40**. This example shows two over-passivation metal layers, while one metal layer, three metal layers, four metal layers or more metal layers over the passivation layer **5** can be formed using the same or similar methods, and the same or similar specification described in FIGS. **15**C-**15**K. In other words, the following description and specification apply to all embodiments in this disclosure.

[0391] Referring to FIG. **15**K, the over-passivation scheme **102** can be formed over the wafer **10** described in FIG. **15**A or FIG. **15**B. The over-passivation scheme **102** includes over-passivation metals **80** and over-passivation polymers or insulators **90**. The over-passivation metals **80** include one, two, three, four or more metal layers. In the example of including two metal layers, the over-passivation metals **80** include a first metal layer **801** and a second metal layer **802**. The specification of the metal layer **801** and the process of forming the same can be applied to the metal layers **811**, **821** and **831** in the disclosure, and the specification of the metal layer **802** and the process of forming the same can be applied to the metal layers **812** and **832** in the disclosure.

[0392] The metals used in the over-passivation metal layers **80** are mainly copper, gold, silver, palladium, rhodium, platinum, ruthenium, and nickel. The metal line, trace, or plane in the over-passivation metal scheme **80** usually includes composite layers of metals in a stack. The cross-section in FIG. **15**K shows two composite layers **8001** and **8002** in each of the

over-passivation metal layers **80**, which can be applied to as the two composite layers **8111** and **8112** of the patterned circuit layer **811**, respectively, as the two composite layers **8211** and **8212** of the patterned circuit layer **821**, respectively, as the two composite layers **8121** and **8122** of the patterned circuit layer **812**, respectively, as the two composite layers **8311** and **8312** of the patterned circuit layer **831**, respectively, and as the two composite layers **8321** and **8322** of the patterned circuit layer **832**, respectively.

[0393] The bottom layer of each over-passivation metal layers **80** is an adhesion/barrier/seed layer **8001** (including **8011** and **8021**), including an adhesion/barrier layer (not shown) and a seed layer (not shown) on the adhesion/barrier layer. The specification of the adhesion/barrier/seed layers **8001** (including **8011** and **8021**) and the process of forming the same can be applied to the adhesion/barrier/seed layers **8111**, **8121**, **8211**, **8311** and **8321**. The top layer of each over-passivation metal layers **80** is a bulk metal layer **8002**, including **8012** and **8022**. The specification of the bulk metal layers **8002** (including **8012** and **8022**) and the process of forming the same can be applied to the bulk metal layers **8112**, **8122**, **8212**, **8312** and **8322**.

[0394] The material of the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** can be Ti (titanium), W, Co, Ni, TiN (titanium nitride), TiW (titanium-tungsten alloy), V, Cr (chromium), Cu, CrCu, Ta (tantalum), TaN (tantalum nitride), or alloy or composite layer of above materials. The adhesion/barrier layer can be formed by a suitable process or processes, e.g., by electroplating, electroless plating, chemical vapor deposition (CVD), or PVD (such as sputtering or evaporation), exemplary deposited by PVD (physical vapor deposition) such as metal sputtering process. The thickness of the adhesion/barrier layer is smaller than 1 micrometer, such as between 0.02 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers.

[0395] For example, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness between 0.02 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **95** and on the pads, principally made of aluminum, exposed by openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of aluminum, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of aluminum, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of aluminum, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of aluminum, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of aluminum, exposed by the openings **950** in the polymer layer **95**.

[0396] For example, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of copper, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of copper, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of copper, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of copper, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of copper, exposed by the openings **950** in the polymer layer **95**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the pads, principally made of copper, exposed by the openings **950** in the polymer layer **95**.

[0397] For example, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer), exposed by the openings **950** in the polymer layer **95**, of the metal caps **66** over the copper pads. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer

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with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer) of the metal caps **66**, exposed by the openings **950** in the polymer layer **95**, over the copper pads. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer), exposed by the openings **950** in the polymer layer **95**, of the metal caps **66** over the copper pads. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer) of the metal caps **66**, exposed by the openings **950** in the polymer layer **95**, over the copper pads. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer), exposed by the openings **950** in the polymer layer **95**, of the metal caps **66** over the copper pads. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8011** may be formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **95** and on the aluminum-containing layer (such as aluminum layer, aluminum-copper alloy layer or Al—Si—Cu alloy layer) of the metal caps **66**, exposed by the openings **950** in the polymer layer **95**, over the copper pads.

[0398] For example, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on a polymer layer **98** and on a gold layer of the conduction bulk layer **8012** exposed by openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the gold layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the gold layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the gold layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the gold layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the gold layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**.

[0399] For example, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on a polymer layer **98** and on a copper layer of the conduction bulk layer **8012** exposed by multiple openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the copper layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the copper layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the copper layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the copper layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**. Alternatively, the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8021** may be formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **98** and on the copper layer of the conduction bulk layer **8012** exposed by the openings **980** in the polymer layer **98**.

[0400] The seed layer at the top of the adhesion/barrier/seed layer **8001**, for the subsequent electroplating process, usually formed by a suitable process or processes, e.g., by electroplating, electroless, CVD, or PVD (such as sputter-

ing), exemplary deposited by PVD such as metal sputtering process. The material used for the seed layer, usually made of the same metal material as the conduction bulk metal formed in the subsequent electroplating process, can be Au, Cu, Ag, Ni, Pd, Rh, Pt or Ru. The material of the seed layer varies with the material of the electroplated metal layer formed on the seed layer. When a gold layer is to be electroplated on the seed layer, gold is a preferable material to the seed layer. When a copper layer is to be electroplated on the seed layer, copper is a preferable material to the seed layer. The thickness of the electroplating seed layer is between 0.05 and 1.2 μm, exemplary between 0.05 and 0.8 μm.

[0401] For example, when the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a gold layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a gold layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium-tungsten-alloy layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a gold layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium-nitride layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a gold layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the chromium layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a gold layer with a thickness of between 0.05 and 1.4 μm, and preferably of between 0.05 and 0.8 μm, on the tantalum-nitride layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a gold layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the tantalum layer.

[0402] For example, when the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a titanium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a copper layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a titanium-tungsten-alloy layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a copper layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium-tungsten-alloy layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a titanium-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a copper layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium-nitride layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a copper layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the chromium layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a tantalum-nitride layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a copper layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.4 μm, on the tantalum-nitride layer. When the adhesion/barrier layer at the bottom of the adhesion/barrier/seed layer **8001** is formed by a suitable process or processes, e.g., by sputtering a tantalum layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, the seed layer at the top of the adhesion/barrier/seed layer **8001** can be formed by a suitable process or processes, e.g., by sputtering a copper layer with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the tantalum layer.

[0403] The conduction bulk layer **8002** is formed for the low resistance conduction, usually formed by a suitable process or processes, e.g., by electroplating, with a thickness between 2 and 100 μm, exemplary between 3 and 20 μm. The metal material of the conduction bulk layer **8002**, formed by a suitable process or processes, e.g., by a process including an electroplating process or an electroless plating process, includes Au, Cu, Ag, Ni, Pd, Rh, Pt or Ru.

[0404] For example, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a gold layer with a thickness of between 2 and 100 μm, and preferably of between 3 and 20 μm, on the seed layer, made of gold, at the top of the adhesion/barrier/seed layer **8001**. Alternatively, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 2 and 100 μm, and preferably of between 3 and 20 μm, on the seed layer, made of copper, at the top of the adhesion/barrier/seed layer **8001**. Alternatively, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 1.5 and 90 μm, and preferably of between 2.5 and 10 μm, on the seed layer, made of copper, at the top of the adhesion/barrier/seed layer **8001**, and then electroplating a gold layer with a thickness of between 0.5 and 10 μm on the copper layer, and the thickness of the copper layer and the gold layer is between 2 and 100 μm, and preferably of between 3 and 20 μm. Alternatively, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 3 and 20 μm, and preferably of between 3 and 15 μm, on the seed layer, made of copper, at the top of the adhesion/barrier/seed layer **8001**, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 1 and 30.8 μm, on the copper layer, and then electroplating a gold layer with a thickness of between 0.03 and 0.5 μm, and preferably of between 0.05 and 0.1 μm, on the nickel layer. Alternatively, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 3 and 20 μm, and preferably of between 3 and 15 μm, on the seed layer, made of copper, at the top of the adhesion/barrier/seed layer **8001**, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 1 and 30.8 μm, on the copper layer, and then electroless plating a gold layer with a thickness of between 0.03 and 0.5 μm, and preferably of between 0.05 and 0.1 μm, on the nickel layer. Alternatively, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 3 and 20 μm, and preferably of between 3 and 15 μm, on the seed layer, made of copper, at the top of the adhesion/barrier/seed layer **8001**, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 1 and 3 μm, on the copper layer, and then electroplating a palladium layer with a thickness of between 0.03 and 0.5 μm, and preferably of between 0.05 and 0.1 μm, on the nickel layer. Alternatively, the conduction bulk layer **8002** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 3 and 20 μm, and preferably of between 3 and 15 μm, on the seed layer, made of copper, at the top of the adhesion/barrier/seed layer **8001**, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 1 and 3 μm, on the copper layer, and then electroless plating a palladium layer with a thickness of between 0.03 and 0.5 μm, and preferably of between 0.05 and 0.1 μm, on the nickel layer.

[0405] As an option, a cap/barrier metal layer (not shown) for protection or diffusion barrier purpose is added. The cap/barrier layer can be formed by a suitable process or processes, e.g., by electroplating, electroless plating, CVD or PVD sputtered metal, exemplary deposited by electroplating. The thickness of the cap/barrier layer is of a range between 0.05 and 50.8 μm, exemplary 0.5 and 3 μm. The cap/barrier layer can be a Ni, Co or V layer. As another option, an assembly-contact layer (not shown) over the conduction bulk metal layer **8002** and the cap/barrier layer (not shown) for assembly or packaging purpose, especially for the top-most metal layer of the over-passivation metals **80** (in one or more metal layers with polymer dielectric between two adjacent metal layers).

[0406] Openings **990** (including **9919** and **9929** in the first embodiment, **9939** and **9939'** in the third embodiment, **9949** and **9949'** in the fourth embodiment) in the topmost polymer layer **99** expose the contact points **8000** (including the contact points **8110** and **8120** in the first embodiment, the contact points **8310** and **8320** in the third embodiment, and the contact points **8110** and **8120** in the fourth embodiment) of the topmost over-passivation metal layer. The assembly-contact metal layer is wirebondable and/or solder wettable used for wirebonding, gold connection, solder ball mounting, and/or solder connection. The assembly-contact metal layer can be Au, Ag, Pt, Pd, Rh or Ru. Joining to the assembly-contact metal layer exposed by the polymer openings **900** can be a bonding wire, a solder ball (solder ball mounting), a metal ball (metal ball mounting), a metal bumps on the other substrate or chip, a gold bump on the other substrate or chip, a metal post on the other substrate or chip, a copper post on the other substrate or chip.

[0407] The over-passivation metal lines, traces or planes can be, as some examples, one of the following stacks, from bottom to top: (1) TiW/sputtered seed Au/electroplated Au, (2) Ti/sputtered seed Au/electroplated Au, (3) Ta/sputtered seed Au/electroplated Au, (4) Cr/sputtered seed Cu/electroplated Cu, (5) TiW/sputtered seed Cu/electroplated Cu, (6) Ta/sputtered seed Cu/electroplated Cu, (7) Ti/sputtered seed Cu/electroplated Cu, (8) Cr, TiW, Ti or Ta/sputtered seed Cu/electroplated Cu/electroplated Ni, (9) Cr, TiW, Ti or Ta/sputtered seed Cu/electroplated Cu/electroplated Ni/electroplated Au, Ag, Pt, Pd, Rh or Ru, (10) Cr, TiW, Ti or Ta/sputtered seed Cu/electroplated Cu/electroplated Ni/electroless Au, Ag, Pt, Pd, Rh or Ru. Each of over-passivation metal layers **80** has thickness between 2 and 150 μm, exemplary between 3 and 20 μm, with horizontal design rules (the width) of over-passivation metal lines or traces between 1 and 200 μm, exemplary 2 and 50 μm. An over-passivation metal plane is also exemplary, particularly for power, or ground plane, with a width larger than 200 μm. The minimum space between two adjacent metal lines, traces and/or planes is between 1 and 500 μm, exemplary 2 and 150 μm.

[0408] In some application of this disclosure, the metal lines, traces or planes can only include sputtered aluminum with thickness between 2 and 6 μm, exemplary between 3 and 5 μm, with an optional adhesion/barrier layer (including Ti, TiW, TiN, Ta or TaN layer) under the aluminum layer.

[0409] Referring to FIG. **15**L, as an option, a contact structure **89** can be formed on the contact point **8000**, exposed by the opening **990**, of the over-passivation metal scheme **80**. The contact structure **89** can be a metal bump, a solder bump, a solder ball, a gold bump, a copper bump, a metal pad, a solder pad, a gold pad, a metal post, a solder post, a gold post or a copper post. The contact structure **89** may include metal layers **891** and **89***c*. The metal layer **891** under the metal layer **89***c* includes Au, Ti, TiW, TiN, Cr, Cu, CrCu, Ta, TaN, Ni, NiV, V or Co layer, or composite layers of the above materials. The exemplary stacks of the contact structure **89** (including metal layers **891** and **89***c*), from the bottom to the top are (1) Ti/Au pad (Au layer thickness 1-10 μm), (2) TiW/Au pad

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(Au layer thickness 1-10 μm), (3) Ni/Au pad (Ni layer thickness 0.5-10 μm, Au layer thickness 0.2-10 μm), (4) Ti/Au bump (Au layer thickness 7-40 μm), (5) TiW/Au bump (Au layer thickness 7-40 μm), (6) Ni/Au bump (Ni layer thickness 0.5-10 μm, Au layer thickness 7-40 μm), (7) Ti, TiW or Cr/Cu/Ni/Au pad, (copper layer thickness 0.1-10 μm, Au layer thickness 0.2-10 μm), (8) Ti, TiW, Cr, CrCu or NiV/Cu/Ni/Au bump, (copper layer thickness 0.1-10 μm, Au layer thickness 7-40 μm), (9) Ti, TiW, Cr, CrCu or NiV/Cu/Ni/solder pad, (copper layer thickness 0.1-10 μm, solder layer thickness 0.2-30 μm), (10) Ti, TiW, Cr, CrCu or NiV/Cu/Ni/solder bump or solder ball, (copper layer thickness 0.1-10 μm, solder layer thickness 10-500 μm), (11) Ti, TiW, Cr, CrCu or NiV/Cu post, (copper layer thickness 10-300 μm), (11) Ti, TiW, Cr, CrCu or NiV/Cu post/Ni, (copper layer thickness 10-300 μm), (12) Ti, TiW, Cr, CrCu or NiV/Cu post/Ni/Solder (copper layer thickness 10-300 μm, solder layer thickness 1-20 μm), (13) Ti, TiW, Cr, CrCu or NiV/Cu post/Ni/Solder (copper layer thickness 10-300 μm, solder layer thickness 20-100 μm). The assembly methods can be wirebonding, TAB bonding, chip-on-glass (COG), chip-on-board (COB), flip chip on BGA substrate, chip-on-film (COF), chip-on-chip stack interconnection, chip-on-Si-substrate stack interconnection and etc.

[0410] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or titanium-tungsten-alloy layer, with a thickness between 0.02 and 0.8 μm, and preferably between 0.05 and 0.5 μm, on the polymer layer **99** and on the contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of gold, with a thickness between 0.05 and 1.2 μm, and preferably between 0.05 and 0.8 μm, on the titanium-containing layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a gold layer with a thickness between 1 and 10 μm on the seed layer exposed by the opening in the photoresist layer, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the gold layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the gold layer with a dry etching method or a wet etching method, and then removing the titanium-containing layer not under the gold layer with a dry etching method or a wet etching method. As to the wet etching method, the seed layer of gold can be etched with an iodine-containing solution, such as solution containing potassium iodide. When the titanium-containing layer is titanium layer, the titanium layer can be wet etched with a solution containing hydrogen fluoride. When the titanium-containing layer is titanium-tungsten-alloy layer, the titanium-tungsten-alloy layer can be wet etched with a solution containing hydrogen peroxide. As to the dry etching method, the seed layer of gold can be removed with an ion milling process or with an Ar sputtering etching process, and the titanium-containing layer can be etched with a chlorine-containing plasma etching process or with an RIE process. Accordingly, the metal layer **891** can be formed of the titanium-containing layer and the seed layer, made of gold, on the titanium-containing layer, and the metal layer **89***c* can be formed of gold that is on the seed layer of the metal layer **891**.

[0411] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or titanium-tungsten-alloy layer, with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **99** and on the contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of copper, with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the titanium-containing layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a copper layer with a thickness of between 1 and 10 μm, and preferably of between 1 and 50.8 μm, on the seed layer exposed by the opening in the photoresist layer, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 0.5 and 1 μm, on the copper layer in the opening, then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, with a thickness of between 50 and 150 μm, and preferably of between 80 and 130 μm, on the nickel layer in the opening, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the tin-containing layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the copper layer with a dry etching method or a wet etching method, then removing the titanium-containing layer not under the copper layer with a dry etching method or a wet etching method, and then reflowing the tin-containing layer. As to the wet etching method, the seed layer of copper can be etched with a solution containing NH_4OH. When the titanium-containing layer is titanium layer, the titanium layer can be wet etched with a solution containing hydrogen fluoride. When the titanium-containing layer is titanium-tungsten-alloy layer, the titanium-tungsten-alloy layer can be wet etched with a solution containing hydrogen peroxide. As to the dry etching method, the seed layer of copper can be removed with an Ar sputtering etching process, and the titanium-containing layer can be etched with a chlorine-containing plasma etching

process or with an RIE process. Accordingly, the metal layer **891** can be formed of the titanium-containing layer and the seed layer, made of copper, on the titanium-containing layer, and the metal layer **89***c* can be formed of the copper layer on the seed layer, the nickel layer on the copper layer, and the tin-containing layer on the nickel layer.

[0412] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **99** and on the contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of copper, with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the chromium layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a copper layer with a thickness of between 1 and 10 μm, and preferably of between 1 and 5 μm, on the seed layer exposed by the opening in the photoresist layer, then electroplating a nickel layer with a thickness of between 0.5 and 50.8 μm, and preferably of between 0.5 and 1 μm, on the copper layer in the opening, then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, with a thickness of between 50 and 150 μm, and preferably of between 80 and 130 μm, on the nickel layer in the opening, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the tin-containing layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the copper layer with a dry etching method or a wet etching method, then removing the chromium layer not under the copper layer with a dry etching method or a wet etching method, and then reflowing the tin-containing layer. As to the wet etching method, the seed layer of copper can be etched with a solution containing NH_4OH, and the chromium layer can be etched with a solution containing potassium ferricyanide. As to the dry etching method, the seed layer of copper can be removed with an Ar sputtering etching process. Accordingly, the metal layer **891** can be formed of the chromium layer and the seed layer, made of copper, on the chromium layer, and the metal layer **89***c* can be formed of the copper layer on the seed layer, the nickel layer on the copper layer, and the tin-containing layer on the nickel layer.

[0413] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **99** and on the contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of copper, with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.4 μm, on the tantalum-containing layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a copper layer with a thickness of between 1 and 10 μm, and preferably of between 1 and 5 μm, on the seed layer exposed by the opening in the photoresist layer, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 0.5 and 1 μm, on the copper layer in the opening, then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, with a thickness between 50 and 150 micrometers, and preferably between 80 and 130 micrometers, on the nickel layer in the opening, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the tin-containing layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the copper layer with a dry etching method or a wet etching method, then removing the tantalum-containing layer not under the copper layer with a dry etching method or a wet etching method, and then reflowing the tin-containing layer. As to the wet etching method, the seed layer of copper can be etched with a solution containing NH_4OH. As to the dry etching method, the seed layer of copper can be removed with an Ar sputtering etching process. Accordingly, the metal layer **891** can be formed of the tantalum-containing layer and the seed layer, made of copper, on the tantalum-containing layer, and the metal layer **89***c* can be formed of the copper layer on the seed layer, the nickel layer on the copper layer, and the tin-containing layer on the nickel layer.

[0414] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as titanium layer or titanium-tungsten-alloy layer, with a thickness between 0.02 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **99** and on the contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of copper, with a thickness between 0.05 and 1.2 micrometers, and preferably between 0.05 and 0.8 micrometers, on the titanium-containing layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating

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the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 0.5 and 1 μm, on the seed layer exposed by the opening in the photoresist layer, then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, with a thickness of between 50 and 150 μm, and preferably of between 80 and 130 μm, on the nickel layer in the opening, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the tin-containing layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the copper layer with a dry etching method or a wet etching method, then removing the titanium-containing layer not under the copper layer with a dry etching method or a wet etching method, and then reflowing the tin-containing layer. As to the wet etching method, the seed layer of copper can be etched with a solution containing NH_4OH. When the titanium-containing layer is titanium layer, the titanium layer can be wet etched with a solution containing hydrogen fluoride. When the titanium-containing layer is titanium-tungsten-alloy layer, the titanium-tungsten-alloy layer can be etched with a solution containing hydrogen peroxide. As to the dry etching method, the seed layer of copper can be removed with an Ar sputtering etching process, and the titanium-containing layer can be etched with a chlorine-containing plasma etching process or with an RIE process. Accordingly, the metal layer **891** can be formed of the titanium-containing layer and the seed layer, made of copper, on the titanium-containing layer, and the metal layer **89***c* can be formed of the nickel layer on the seed layer and the tin-containing layer on the nickel layer.

[0415] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a chromium layer with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **99** and on contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of copper, with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the chromium layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 0.5 and 1 μm, on the seed layer exposed by the opening in the photoresist layer, then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, with a thickness of between 50 and 150 μm, and preferably of between 80 and 130 μm, on the nickel layer in the opening, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the tin-containing layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the copper layer with a dry etching method or a wet etching method, then removing the chromium layer not under the copper layer with a dry etching method or a wet etching method, and then reflowing the tin-containing layer. As to the wet etching method, the seed layer of copper can be etched with a solution containing NH_4OH, and the chromium layer can be etched with a solution containing potassium ferricyanide. As to the dry etching method, the seed layer of copper can be removed with an Ar sputtering etching process. Accordingly, the metal layer **891** can be formed of the chromium layer and the seed layer, made of copper, on the chromium layer, and the metal layer **89***c* can be formed of the nickel layer on the seed layer and the tin-containing layer on the nickel layer.

[0416] For example, the contact structure **89** may be formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, with a thickness of between 0.02 and 0.8 μm, and preferably of between 0.05 and 0.5 μm, on the polymer layer **99** and on the contact point **8000** of copper, nickel or gold exposed by the opening **990**, then sputtering a seed layer, made of copper, with a thickness of between 0.05 and 1.2 μm, and preferably of between 0.05 and 0.8 μm, on the tantalum-containing layer, then spin-on coating a photoresist layer, such as positive-type photoresist layer, on the seed layer, then exposing the photoresist layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photoresist layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photoresist layer, then developing the exposed photoresist layer, an opening in the developed photoresist layer exposing the seed layer over the contact point **8000**, then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then electroplating a nickel layer with a thickness of between 0.5 and 5 μm, and preferably of between 0.5 and 1 μm, on the seed layer exposed by the opening in the photoresist layer, then electroplating a tin-containing layer, such as a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, with a thickness of between 50 and 150 μm, and preferably of between 80 and 130 μm, on the nickel layer in the opening, then removing the developed photoresist layer using an organic solution with amide, then removing the residual polymeric material or other contaminants from the seed layer and from the tin-containing layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, then removing the seed layer not under the copper layer with a dry etching method or a wet etching method, then removing the tantalum-containing layer not under the copper layer with a

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dry etching method or a wet etching method, and then reflowing the tin-containing layer. As to the wet etching method, the seed layer of copper can be etched with a solution containing NH_4OH. As to the dry etching method, the seed layer of copper can be removed with an Ar sputtering etching process. Accordingly, the metal layer **891** can be formed of the tantalum-containing layer and the seed layer, made of copper, on the tantalum-containing layer, and the metal layer **89***c* can be formed of the nickel layer on the seed layer and the tin-containing layer on the nickel layer.

[0417] There is another important feature of the over-passivation scheme **8**: using polymer material as the dielectric or insulating layer **90**, over, under or between the over-passivation metal layers **80**. Referring to FIG. **15**K, use of polymer layers **90** (including **95**, **98** and **99** in all embodiments of this disclosure) provides the possibility of fabricating thicker than 2 μm dielectric layer. The thickness of the polymer layer **90** can be between 2 and 100 μm, and preferably of between 3 and 30 μm. The polymer layers **90** used in the over-passivation scheme **102** can be polyimide (PI), benzocyclobutene (BCB), elastomer (such as silicone), parylene, epoxy-based material (such as photoepoxy SU-8 supplied by Sotec Microsystems, Renens, Switzerland). A solder mask material used in the printing circuit board industry can be used as the cap layer **99** (the topmost polymer layer over all the over-passivation metal layers **80**). A photosensitive polyimide can be used as the polymer layers **90** (including **95**, **98** and **99** in all embodiments of this disclosure). Furthermore, the polymer layers **90** (including **95**, **98** and **99** in all embodiments of this disclosure) can be a non-ionic polyimide, such as an ether-based polyimide, PIMEL™, supplied by Asahi Chemical, Japan. Copper does not diffuse or penetrate through the non-ionic polyimide, therefore, it is allowed to have a direct contact between copper and polyimide. With the non-ionic polyimide, spacing between copper lines or traces or planes in the over-passivation metal scheme **80** can be as close as 1 μm, i.e. the spacing between two metal traces or planes can be larger 1 μm. Furthermore, no protection cap, such as nickel layer, over the copper layer is required for copper lines, traces or planes.

[0418] Referring to FIG. **15**K now, openings **900** in the polymer layers **90** are formed for interconnection between different over-passivation metal layers **80**, or for connection to the underlying fine-line metal layers **60**, or for connection to an external circuits. The polymer openings **900** (including **950**, **980** and **990**) includes (1) **9919**, **9929**, **9829**, **9519**, **9519'**, **9511**, **9512** and **9514** in the first embodiment; (2) **9831**, **9834**, **9531**, **9532** and **9534** in the second embodiment; (3) **9939**, **9939'**, **9839**, **9831**, **9834**, **9539**, **9539'**, **9531**, **9532** and **9534** in the third embodiment; and (4) **9949**, **9949'**, **9849'**, **9511**, **9512**, **9514** and **9549** in the fourth embodiment. The material of the polymer layers **90** can be a photo-sensitive or non-photo-sensitive. For the photo-sensitive polymer layers **90**, the polymer openings **900** are defined and patterned by light exposure and developing. While for the non-photo-sensitive polymer layer **90**, the openings **900** are defined by first coating a photoresist layer over the polymer layer, exposing and developing the photoresist to create openings in the photoresit, wet or dry etching the polymer layer exposed by the photoresist openings, creating openings **900** in the polymer layer **90**, and then stripping the photoresist. The width of the polymer openings **900** is between 2 and 1,000 μm, exemplary between 5 and 200 μm. In some designs, the polymer layer **90** may be removed in a large with dimension larger than 1,000 μm. The openings **900** are designed in circles, corner-rounded squares, rectangles, or polygons.

[0419] The polymer layer **95** is between the passivation layer **5** and the bottom-most over-passivation metal layer **801**. Through openings **950** in the polymer layer **95**, the signal, power (Vdd or Vcc) and/or ground (Vss) passes between the fine-line metal scheme **6** and the over-passivation metal scheme **80**. The process for forming the openings **950** in the polymer layer **95** can be applied to the process for (1) forming the openings **9519**, **9519'**, **9511**, **9512** and **9514** in FIG. **3**D in the polymer layer **95**; (2) forming the openings **9531**, **9532** and **9534** in FIG. **7**D in the polymer layer **95**; (3) forming the openings **9539**, **9539'**, **9531**, **9532** and **9534** in FIGS. **10**D, **10**E, **10**G, **10**H and **10**I in the polymer layer **95**; or (4) forming the opening **9549**, **9511**, **9512** and **9514** in FIG. **14**D in the polymer layer **95**. The width of the polymer openings **9531**, **9532**, **9534**, **9511**, **9512** and **9514**, aligned with the passivation openings **531**, **532**, **534**, **511**, **512** and **514**, respectively, for the internal circuits **20** (including **21**, **22**, **23** and **24**) is between 1 and 300 μm, exemplary between 3 and 100 μm. The width of the openings **9519** and **9519'**, aligned with the openings **519** and **519'**, respectively, for the voltage regulator or converter circuit **41**, the width of the openings **9539** and **9539'**, aligned with the openings **539** and **539'**, respectively, for the off-chip circuit **40** (including **42** and **43**), or the width of the opening **9549**, aligned with the opening **549**, respectively, for the ESD circuit **44** may be larger than those of the openings **9531**, **9532**, **9534**, **9511**, **9512** and **9514**, in a range between 5 and 1,000 micrometers, exemplary 10 and 200 micrometers. Note that two types of stacked vias of a polymer opening **950** over a passivation opening **50**. In a first type of stacked vias, the polymer openings, for example the opening **9531** shown in FIG. **10**E, has a width larger than that of the underlying passivation opening **531** shown in FIG. **10**E. The opening **9531** exposes a top surface of the passivation layer **5** adjacent to the contact pad **6390** exposed by the opening **531**, in addition to exposing the contact pad **6390**. In this case, a smaller passivation opening **531** can be formed; hence a smaller contact pad of the top-most fine-line metal layer **60** can be formed. This type of stacked vias allows higher routing density of the top-most fine-line metal layer **60**. In a second type of stacked vias, the polymer openings, for example the opening **9539** shown in FIG. **10**E, is smaller than the underlying passivation opening **539** shown in FIG. **10**E. The polymer layer **95** covers a peripheral region of the contact pad **6390** exposed by the opening **539** and the passivation layer **5**, an opening **9531** in the polymer layer **95** exposing a center region of the contact pad **6390** exposed by the opening **539**. In this type, the polymer layer **95** covers the sidewall of the passivation openings. The sidewall of the polymer openings provides a gentle, better slope than the slope of the passivation opening sidewall, and resulting in a better step coverage for the subsequent metal sputtering for the adhesion/barrier/seed layer **8011**. A better adhesion/barrier metal step coverage is important for the reliability of the chip, since it prevent the inter-metallic compound (IMC) from happening.

[0420] The openings **980** in the polymer layer **98** are between two over-passivation metal layers **801** and **802**. The process for forming the openings **980** in the polymer layer **98** can be applied to the process for (1) forming the opening **9829** in FIG. **3**C in the polymer layer **98**; (2) forming the openings **9831** and **9834** in FIG. **7**C in the polymer layer **98**; (3) forming the openings **9831**, **9834** and **9839** in FIGS. **10**C and **10**E

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in the polymer layer **98**; or (4) forming the opening **9849'** in FIG. **14**C in the polymer layer **98**. The width of the polymer openings **9831** and **9834** for the internal circuits **20** (including **21**, **22**, **23** and **24**) is between 1 and 300 μm, exemplary between 3 and 100 μm. The width of the polymer opening **9829** for the voltage regulator or converter circuit **41**, the width of the polymer opening **9839** for the off-chip circuit **40** (including **42** and **43**), or the width of the polymer opening **9849'** for the ESD circuit **44** may be larger than those of the openings **9831** and **9834**, in a range between 5 and 1,000 μm, exemplary 10 and 200 μm.

[0421] The opening **990** in the cap polymer layer **99** exposes the contact point **8000** of the top-most metal layer **802** for connecting to the external circuits or for the probe contacting in chip testing. The process for forming the openings **990** in the polymer layer **99** can be applied to the process for (1) forming the opening **9919** in FIGS. **3**B and **3**D in the polymer layer **99**; (2) forming the opening **9929** in FIG. **3**C in the polymer layer **99**; (3) forming the opening **9939** in FIGS. **10**B, **10**D, **10**F, **10**G, **10**H and **10**I in the polymer layer **99**; (4) forming the opening **9939'** in FIGS. **10**C and **10**E in the polymer layer **99**; (5) forming the opening **9949** in FIGS. **14**B and **14**D in the polymer layer **99**; or (6) forming the opening **9949'** in FIG. **14**C in the polymer layer **99**. There are no openings in the cap polymer layer **99** for the internal circuits **20** (including **21**, **22**, **23** and **24**) being connected to an external circuit. The width of the polymer openings **9919** and **9929** for the voltage regulator or converter circuit **41**, the width of the polymer openings **9939** and **9939'** for the off-chip circuit **40** (including **42** and **43**), or the width of the polymer openings **9949** and **9949'** for the ESD circuit **44**, can be in a range between 5 and 1,000 μm, exemplary 10 and 200 μm.

[0422] The signal, power or ground stimuli in the over-passivation metal layers **80** of the over-passivation scheme **102** is delivered to the internal circuits **20**, the voltage regulator or converter circuit **41**, the off-chip circuits **40** or the ESD circuits **44** through the fine-line scheme **6**. The fine-line metals **631**, **632**, **634**, **639** and **639'** shown in FIG. **15**A can be composed of stacked via plugs **60'**, and preferably, the upper one may be directly over the lower one. Alternative, the fine-line metal **632** may include a local fine-line metal layer **632***c* shown in FIG. **15**A, and as well as in all embodiments of this disclosure.

[0423] The photolithography used to fabricate the over-passivation scheme **102** is significantly different from that of convention IC process. Similarly, the over-passivation photolithography process includes coating, exposing and developing the photoresist. Two types of photoresist are used to form the over-passivation scheme **8**: (1) liquid photoresist, formed by a suitable process or processes, e.g., by one or multiple spin-on coating, or printing. The liquid photoresist has a thickness between 3 and 60 μm, exemplary between 5 and 40 μm; (2) dry-film photoresist, formed by a suitable process or processes, e.g., by a laminating method. The dry-film photoresist has a thickness between 30 and 300 μm, exemplary between 50 and 150 μm. The photoresist can be positive-type or negative-type, exemplary positive-type thick photoresist for better resolution. If the polymer is photo-sensitive, the same photolithography process for the photoresist can be applied to pattern the polymer. An aligner or 1× stepper exposes the photoresist. The 1× means that the dimension on a photo mask (usual made of quartz or glass) is reduced on the wafer when light beam is projected from the photo mask onto the wafer, and the dimension of a feature on the photo mask is the same of the dimension on the wafer. The wavelength of the light beam used in the aligner or 1× stepper can be a 436 nm (g-line), 397 nm (h-line), 365 nm (i-line), g/h-line (combination of g-line and h-line), or g/h/i-line (combination of g-line, h-line and i-line). The g/h-line or g/h/i-line 1× stepper (or 1× aligner) provides strong light intensity for thick photoresist or thick photo-sensitive polymer exposure.

[0424] Sine the passivation layer **5** protects underlying MOS transistors and fine-line scheme **6** from the penetration of moisture, sodium or other mobile ions, gold, copper or other transition metals, the over-passivation scheme **102** on the wafer can be processed in a clean room with Class **10** or less stringent environment, for example Class **100**. A Class **100** clean room allows maximum number of particles per cubic foot: 1 larger than 5 μm, 10 larger than 1 μm, 100 larger than 0.5 μm, 300 larger than 0.3 μm, 750 larger than 0.2 μm, 3500 larger than 0.1 μm.

[0425] The device layer **2** includes the internal circuits **20** (including **21**, **22**, **23** and **24**) in all embodiments, the voltage regulator or converter circuit **41** in the first embodiment, the off-chip circuits **40** (including **42** and **43**) in the third embodiment, and the ESD circuit **44** in the fourth embodiment.

[0426] An internal circuit or an internal circuit unit **20**, including **21**, **22**, **23** and **24**, in all embodiments of this disclosure, is defined as a circuit whose signal nodes are not connected to the external (outside the chip) circuits. If a signal of an internal circuit or internal circuit unit **20** needs to connect to an external circuit, it must go through an off-chip circuit first, for example, ESD circuits, off-chip drivers or off-chip receivers and/or other off-chip I/O circuits, before connecting to the external circuit. In other definition, the internal circuits or the internal circuit units **20** do not include off-chip circuits. The internal circuits or internal circuit units **20**, including **21**, **22**, **23** and **24**, in this disclosure may, in addition to a NOR gate and a NAND gate, be an inverter, an AND gate, an OR gate, an SRAM cell, a DRAM cell, a non-volatile memory cell, a flash memory cell, an EPROM cell, a ROM cell, a magnetic RAM (MRAM) cell, a sense amplifier, an operational amplifier, an adder, a multiplexer, a diplexer, a multiplier, an A/D converter, a D/A converter, or other CMOS, BiCMOS, and/or bipolar circuit, analog circuit, a CMOS sensor cell, or a photo-sensitive diode.

[0427] Moreover, an internal circuit or an internal circuit unit **20** can be defined by its peak input or output current, or it can be defined as its MOS transistor size, as discussed in the third embodiment. The off-chip circuits **40**, including the off-chip buffer **42** and the off-chip ESD circuit **43**, can also be defined by its peak input or output current, or defined as its MOS transistor size, also as discussed in the third embodiment. The definition of the internal circuit **20** and the off-chip circuit **40** apply to all other embodiments in this disclosure.

[0428] In a case, a gate of a MOS device may be connected to another gate of another MOS device through the above mentioned thick and wide metal trace, bus or plane **81**, **81**P, **82**, **83**, **83'** or **85** over the passivation layer **5**. In another case, a gate of a MOS device may be connected to a source of another MOS device through the above mentioned thick and wide metal trace, bus or plane **81**, **81**P, **82**, **83**, **83'** or **85** over the passivation layer **5**. In another case, a gate of a MOS device may be connected to a drain of another MOS device through the above mentioned thick and wide metal trace, bus or plane **81**, **81**P, **82**, **83**, **83'** or **85** over the passivation layer **5**. In another case, a source of a MOS device may be connected

to another source of another MOS device through the above mentioned thick and wide metal trace, bus or plane **81**, **81**P, **82**, **83**, **83'** or **85** over the passivation layer **5**. In another case, a source of a MOS device may be connected to a drain of another MOS device through the above mentioned thick and wide metal trace, bus or plane **81**, **81**P, **82**, **83**, **83'** or **85** over the passivation layer **5**. In another case, a drain of a MOS device may be connected to another drain of another MOS device through the above mentioned thick and wide metal trace, bus or plane **81**, **81**P, **82**, **83**, **83'** or **85** over the passivation layer **5**.

[0429] In following paragraphs, the dimension of features and electrical characteristics are described and compared between metal lines or metal traces **80**, **60** in the over-passivation scheme **102** and in the fine-line scheme **6** for exemplary embodiments in this disclosure:

[0430] (1). Thickness of metal lines, metal traces: Each of the over-passivation metal layers **80** has thickness between 2 and 150 μm, exemplary between 3 and 20 μm, while each of the fin-line metal layers **60** has thickness between 0.05 and 2 μm, exemplary between 0.2 and 1 μm. For an IC chip designed with embodiments in this disclosure, the thickness of an over-passivation metal line or metal trace is thicker than the thickness of any fine-line metal lines or metal traces, with the thickness ratio in a range between 2 and 250, exemplary between 4 and 20.

[0431] (2). Thickness of dielectric layers: Each of the over-passivation dielectric (usually an organic material, such as polymer) layers **90** has thickness between 2 and 150 μm, exemplary between 3 and 30 μm, while each of the fine-line dielectric (usually inorganic material, such as oxide or nitride) layers **30** has thickness between 0.05 and 20.8 μm, exemplary between 0.2 and 1 μm. For an IC chip designed with embodiments in this disclosure, the thickness of an over-passivation dielectric layer **90** (separated by two neighboring metal layers) is thicker than the thickness of any fine-line dielectric layer **30** (separated by two neighboring metal layers), with the thickness ratio in a range between 2 and 250, exemplary between 4 and 20.

[0432] (3). Sheet resistance and resistance of metal lines or metal traces: Sheet resistance of a metal line or metal trace is computed by dividing metal resistivity by metal thickness. The sheet resistance of a copper (5 μm thick) over-passivation metal line or trace is about 4 milli-ohms per square, while for a gold (4 μm thick) over-passivation metal line or trace is about 5.5 milli-ohms per square. The sheet resistance of an over-passivation metal line, or trace, or plane is in a range between 0.1 and 10 milli-ohms per square, exemplary between 1 and 7 milli-ohms per square. The sheet resistance of a sputtered aluminum (0.8 μm thick) fine-line metal line or trace is about 35 milli-ohms per square, while for a damascene copper (0.9 μm thick) fine-line metal line or trace is about 20 milli-ohms per square. The sheet resistance of a fine-line metal line, or trace, or plane is in a range between 10 and 400 milli-ohms per square, exemplary between 15 and 100 milli-ohms per square. The resistance per unit length of a metal line or trace is calculated by dividing the sheet resistance by its width. The horizontal design rules (the width) of over-passivation metal lines or traces between 1 and 200 μm, exemplary 2 and 50 μm, while the horizontal design rules (the width) of lines or traces between 20 nano-meter and 15 μm, exemplary 20 nano-meter and 2 μm. The resistance per mm of an over-passivation metal line or trace is between 2 milli-ohms per mm length and 5 ohms per mm length, exemplary between 50 milli-ohms per mm length and 2.5 ohms per mm length. The resistance per mm of a fine-line metal line or trace is between 1 ohm per mm length and 3,000 ohms per mm length, exemplary between 500 milli-ohms per mm length and 500 ohms per mm length. For an IC chip designed with embodiments in this disclosure, the resistance per unit length of an over-passivation metal line or metal trace is smaller than that of any fine-line metal lines or metal traces, with the ratio of resistance per unit length (fine-line to over-passivation) in a range between 3 and 250, exemplary between 10 and 30.

[0433] (4). Capacitance per unit length of metal lines or metal traces: Capacitance per unit length is related to dielectric types, thickness, and metal line width, spacing, and thickness, and the surrounding metals in horizontal and vertical directions. The dielectric constant of polyimide is about 3.3; the dielectric constant of BCB is about 2.5. FIG. **20** shows an example of a typical over-passivation metal line or trace **802***x* with two neighboring metal lines or traces **802***y* and **802***z* on both sides on the same metal layer **802**, and a metal line or trace **801***w* on a metal layer **801** under the metal layer **802**, separating by a polymer layer **98**. Similarly, FIG. **20** shows an example of a typical fine-line metal line or trace **602***x* with two neighboring metal lines or traces **602***y* and **602***z* on both sides on the same metal layer **602**, and a metal line or trace **601***w* on a metal layer **601** under the metal layer **602**, separating by a dielectric layer **30**. The typical capacitance per unit length of the typical metal lines or traces **802***x*, **602***x* include three components: 1) plate capacitance, Cxw (pF/mm) which is a function of the metal width to dielectric thickness aspect ratio, 2) coupling capacitance, Ccx (=Cxy+Cxz), which is a function of the metal thickness to line spacing aspect ratio, and 3) fringing capacitance, Cfx (=Cfl+Cfr), which is a function of metal thickness, spacing, and dielectric thickness. The capacitance per mm of an over-passivation metal line or trace is between 0.1 pF (pico Farads) per mm length and 2 pF per mm length, exemplary between 0.3 pF per mm length and 1.5 pF per mm length. The capacitance per mm of a fine-line metal line or trace is between 0.2 pF per mm length and 4 pF per mm length, exemplary between 0.4 pF per mm length and 2 pF per mm length. For an IC chip designed with embodiments in this disclosure, the capacitance per unit length of an over-passivation metal line or metal trace is smaller than that of any fine-line metal lines or metal traces, with the ratio of capacitance per unit length (fine-line to over-passivation) in a range between 1.5 and 20, exemplary between 2 and 10. An over-passivation scheme **102** shown in FIG. **20** includes the polymer layers **95**, **98** and **99**, the patterned circuit layers **801** and **802**, and the metal bump **89**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the opening **980** in the polymer layer **98** is over the patterned circuit layer **801**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **802**, and the metal bump **89** is in the opening **990**, on the contact point **8000** and on the polymer layer **99**.

[0434] (5). RC constant of metal lines or metal traces: The signal propagation time on a metal line or metal trace is computed by the RC delay. Based on the description of previous two paragraphs (3) and (4), the RC delay in an over-passivation metal line or trace is in a range between 0.003 and 10 ps (pico second) per mm length, exemplary between 0.25 and 2 ps (pico second) per mm length; while the RC delay in a fine-line metal line or trace is in a range between 10 and 2,000 ps (pico second) per mm length, exemplary between 40

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and 500 ps (pico second) per mm length. For an IC chip designed with embodiments in this disclosure, the RC propagation time per unit length of an over-passivation metal line or metal trace is smaller than that of any fine-line metal lines or metal traces, with the ratio of RC propagation delay time per unit length (fine-line to over-passivation) in a range between 5 and 500, exemplary between 10 and 30.

[0435] FIGS. **15**C-**15**K show the process steps to form the over-passivation scheme **102** on the wafer **10** shown in FIG. **15**A or FIG. **15**B. Each of the over-passivation metal layers **80** is formed by a suitable process or processes, e.g., by an embossing process (as contrast to the damascene copper process under the passivation layer **5**).

[0436] Referring to FIG. **15**C, a polymer layer **95** can be formed on the passivation layer **5** of the wafer **10**. If the polymer layer **95** is in liquid form, it can be deposited by spin-on coating or printing. If the polymer layer **95** is a dry film, the dry film is formed by a suitable process or processes, e.g., by a laminating method. For a photo-sensitive polymer, the polymer layer **95** is exposed by light of an aligner or a 1× stepper through a photo mask. Multiple openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** and expose them. If the polymer is non-photo-sensitive, a photolithography process using a photoresist is required to pattern the openings **950**. A hard mask (such as a silicon oxide layer, not shown), with a slow differentiating etch rate during the polymer opening etch, may optionally be deposited on the polymer layer **95** before coating the photoresist. As an alternative, the patterned polymer layer **95** (that is a polymer layer with openings **950**) can also be formed by a suitable process or processes, e.g., by screening printing methods using a metal screen with patterned holes. No exposure and developing are required in the screen-printing method. If the polymer layer **95** is a dry film, as another alternative, holes can be formed in a sheet of dry film before laminated on the wafer. No exposure and developing are required in this alternative.

[0437] For example, the polymer layer **95** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness between 6 and 50 micrometers on the passivation layer **5** and on the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form multiple openings in the exposed polyimide layer exposing the metal pads re traces **600**, then curing or heating the developed polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness between 3 and 25 micrometers, and then removing the residual polymeric material or other contaminants from the upper surfaces of the metal pads or traces **600** exposed by the openings in the polyimide layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the polymer layer **95** can be patterned with the openings **950** in the polymer layer **95** exposing the metal pads or traces **600**. Alternatively, the developed polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient.

[0438] The polymer layer **95** between the bottom-most patterned metal layer **801** and the passivation layer **5** planarizes the surface of the passivation layer **5**, and decouples the over-passivation metal scheme **80** from the underlying fine-line metal scheme **6**, resulting in high electrical performance. In some applications, the polymer layer **95** may be omitted to for cost saving. Note that openings **950** are aligned with the passivation openings **50**. Note also that the polymer openings **950** can be either larger or smaller than the passivation openings **50**. As an alternative, regards to the wafer **10** in FIG. **15**A, there are no openings in the passivation layer **5**, next the polymer layer **95** is spin coated on the passivation layer **5**, followed by forming the openings **950** in the polymer layer **95** exposing the passivation layer **5**, and then forming the openings **50** in the passivation layer **5** under the openings **950**, exposing the contact pads of the fine-line metal scheme **6**. In this option, the polymer openings **950** are about the same size as the openings **50** in the passivation layer **5**.

[0439] FIGS. **15**D-**15**H show an embossing process to form the patterned metal layer **801**. Referring to FIG. **15**D, after forming the polymer layer **95** illustrated in FIG. **15**C, an adhesion/barrier/seed layer **8011** is formed on the polymer layer **95** and on the regions of the metal pads or traces **600** exposed by the openings **950** in the polymer layer **95** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The adhesion/barrier/seed layer **8011** includes an adhesion/barrier layer on the polymer layer **95** and on the regions of the metal pads or traces **600** exposed by the openings **950**, and a seed layer on the adhesion/barrier layer. The material of the adhesion/barrier layer may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0440] For example, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.02 and 0.8 micrometers, on the polymer layer **95** and on the regions of the metal pads or traces **600** exposed by the openings **950**, the seed layer of the adhesion/barrier/seed layer **8011** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.7 micrometers, and preferably between 0.05 and 0.2 micrometers, on the titanium-containing layer.

[0441] Alternatively, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.02 and 0.8 micrometers, on the polymer layer **95** and on the

regions of the metal pads or traces **600** exposed by the openings **950**, the seed layer of the adhesion/barrier/seed layer **8011** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.7 micrometers, and preferably between 0.05 and 0.2 micrometers, on the tantalum-containing layer.

[0442] Alternatively, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.02 and 0.8 micrometers, on the polymer layer **95** and on the regions of the metal pads or traces **600** exposed by the openings **950**, the seed layer of the adhesion/barrier/seed layer **8011** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.7 micrometers, and preferably between 0.05 and 0.2 micrometers, on the chromium-containing layer.

[0443] Referring to FIG. **15**E, after forming the adhesion/barrier/seed layer **8011** illustrated in FIG. **15**D, a photoresist layer **71** is formed on the seed layer of the adhesion/barrier/seed layer **8011**, and multiple openings **710** in the photoresist layer **71** expose the seed layer of the adhesion/barrier/seed layer **8011**. The openings **710** defined the metal lines, traces or planes to be formed in the subsequent process, and contacts in the polymer openings **950** and the passivation openings **50**. The contacts are over and connected to the exposed fine-line metal pads or traces **600**.

[0444] For example, the photoresist layer **71** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer on the seed layer of the adhesion/barrier/seed layer **8011**, then exposing the photosensitive polymer layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photosensitive polymer layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photosensitive polymer layer, then developing the exposed polymer layer, and then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the photoresist layer **71** can be patterned with the openings **710** exposing the seed layer of the adhesion/barrier/seed layer **8011**.

[0445] Referring to FIG. **15**F, a bulk metal layer **8012** can be formed on the seed layer, exposed by the openings **710** in the photoresist layer **71**, of the adhesion/barrier/seed layer **8011** and in the openings **710** by a process including an electroplating process and/or an electroless plating process. The bulk metal layer **8012** may have a thickness larger than 2 micrometers, such as between 2 and 100 micrometers, and preferably between 3 and 20 micrometers, and larger than that of the adhesion/barrier/seed layer **8011** and that of each of the fine-line metal layers **60**, respectively. The bulk metal layer **8012** may have a width larger than 1 micrometer, such as between 5 and 150 micrometers, and preferably between 5 and 50 micrometers, and larger than that of each of the fine-line metal layers **60**.

[0446] The bulk metal layer **8012** having a thickness larger than 2 micrometers, such as between 2 and 200 micrometers, between 2 and 50 micrometers or between 2 and 30 micrometers, may be a single layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel, or a composite layer made of the previously described metals.

[0447] For example, the bulk metal layer **8012** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness larger than 2 micrometers, such as between 2 and 50 micrometers, and preferably between 2 and 30 micrometers, in the openings **710** and on the seed layer, preferably the previously described gold layer, of the adhesion/barrier/seed layer **8011** exposed by the openings **710**.

[0448] Alternatively, the bulk metal layer **8012** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 2 micrometers, such as between 2 and 200 micrometers, and preferably between 2 and 30 micrometers, in the openings **710** and on the seed layer, preferably the previously described copper layer, of the adhesion/barrier/seed layer **8011** exposed by the openings **710**.

[0449] Alternatively, the bulk metal layer **8012** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness larger than 2 micrometers, such as between 2 and 100 micrometers, and preferably between 2 and 30 micrometers, in the openings **710** and on the seed layer, preferably the previously described copper or nickel layer, of the adhesion/barrier/seed layer **8011** exposed by the openings **710**.

[0450] Alternatively, the bulk metal layer **8012** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 2 micrometers, such as between 2 and 30 micrometers, and preferably between 3 and 15 micrometers, in the openings **710** and on the seed layer, preferably the previously described copper layer, of the adhesion/barrier/seed layer **8011** exposed by the openings **710**, and then electroplating or electroless plating a gold layer, to a thickness larger than 0.5 micrometers, such as between 0.05 and 10 micrometers, and preferably between 0.5 and 1 micrometers, in the openings **710** and on the electroplated copper layer in the openings **710**.

[0451] Alternatively, the bulk metal layer **8012** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 2 micrometers, such as between 2 and 30 micrometers, and preferably between 3 and 15 micrometers, in the openings **710** and on the seed layer, preferably the previously described copper layer, of the adhesion/barrier/seed layer **8011** exposed by the openings **710**, then electroplating or electroless plating a nickel layer, to a thickness larger than 0.5 micrometers, such as between 0.5 and 5 micrometers, and preferably between 1 and 3 micrometers, in the openings **710** and on the electroplated copper layer in the openings **710**, and then electroplating or electroless plating a gold layer, a palladium layer or a platinum layer, to a thickness larger than 0.03 micrometers, such as between 0.03 and 0.5 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **710** and on the electroplated or electroless plated nickel layer in the openings **710**.

[0452] A cap/barrier layer (not shown) can be optionally formed by a suitable process or processes, e.g., by electroplating or electroless plating over the bulk metal layer **8012**. An assembly/contact layer (not shown) can also be further formed, as an option also, over the bulk metal layer **8012** and the cap/barrier layer by electroplating or electroless plating. The assembly/contact layer can be a gold layer, a palladium layer or a ruthenium layer with a thickness between 0.01 and 5 micrometers.

[0453] Next, referring to FIG. **15**G, the photoresist layer **71** is removed using an inorganic solution or using an organic solution with amide. However, some residuals from the photoresist layer **71** could remain on the bulk metal layer **8012** and on the seed layer of the adhesion/barrier/seed layer **8011**. Thereafter, the residuals can be removed from the bulk metal layer **8012** and from the seed layer of the adhesion/barrier/seed layer **8011** with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen.

[0454] Referring to FIG. **15**H, the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** is then removed by self-aligned wet and/or dry etching. In the case of wet etching to remove the bottom metal layer **8011** not under the bulk metal layer **8012**, an undercut **8011'** with a sidewall of the bottom metal layer **8011** recessed from a sidewall of the bulk metal layer **8012** is formed. No undercut **8011'** exists when an anisotropies dry etching is used to remove the bottom metal layer **8011** not under the bulk metal layer **8012**.

[0455] For example, when the seed layer of the adhesion/barrier/seed layer **8011** is a gold layer, it can be etched with an iodine-containing solution, such as solution containing potassium iodide, with an ion milling process or with an Ar sputtering etching process. Alternatively, when the seed layer of the adhesion/barrier/seed layer **8011** is a copper layer, it can be etched with a solution containing NH_4OH or with an Ar sputtering etching process.

[0456] For example, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide, with a chlorine-containing plasma etching process or with an RIE process. Alternatively, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is a titanium layer, it can be etched with a solution containing hydrogen fluoride, with a chlorine-containing plasma etching process or with an RIE process. Alternatively, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is a chromium layer, it can be etched with a solution containing potassium ferricyanide.

[0457] Accordingly, the patterned circuit layer **801** composed of the metal layers **8011** and **8012** can be formed on the polymer layer **95** and on the regions of the metal pads or traces **600** exposed by the openings **950**, and can be connected to the fine-line metal layers **60** through the openings **50** and **950**. Alternatively, the polymer layer **95** can be omitted, that is, the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** can be formed on the passivation layer **5** and on the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**. After the step illustrated in FIG. **15**H, the semiconductor wafer **10** can be optionally cut into a plurality of individual semiconductor chip by a die-sawing process.

[0458] An over-passivation scheme **102** shown in FIG. **15**H includes the polymer layer **95** and the patterned circuit layer **801**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**.

[0459] FIGS. **15**I and **15**J show a process of forming the additional polymer layer **98** and patterned circuit layer **802** using the above mentioned process illustrated in FIGS. **15**C-**15**H. First, after the step illustrated in FIG. **15**H, the polymer layer **98** is formed on the polymer layer **95** and on the bulk metal layer **8012** of the patterned circuit layer **801**, and multiple openings **980** in the polymer layer **98** are over multiple regions of the bulk metal layer **8012** of the patterned circuit layer **801** and expose them. Next, an adhesion/barrier layer of an adhesion/barrier/seed layer **8021** is formed on the polymer layer **98** and on the regions of the bulk metal layer **8012** exposed by the openings **980**. Next, a seed layer of the adhesion/barrier/seed layer **8021** can be formed on the adhesion/barrier layer of the adhesion/barrier/seed layer **8021**. Next, a photoresist layer is formed on the seed layer of the adhesion/barrier/seed layer **8021**, and multiple openings in the photoresist layer expose the seed layer of the adhesion/barrier/seed layer **8021**. Next, a bulk metal layer **8022** is formed on the seed layer of the adhesion/barrier/seed layer **8021** exposed by the openings in the photoresist layer. Next, the photoresist layer is removed using an inorganic solution or using an organic solution with amide. Next, the adhesion/barrier/seed layer **8021** not under the bulk metal layer **8022** is removed. The specification of the polymer layer **98**, the adhesion/barrier/seed layer **8021** and the bulk metal layer **8022** as shown in FIGS. **15**I-**15**L can be referred to as the specification of the polymer layer **95**, the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012**, respectively, as illustrated in FIGS. **15**C-**15**H. The process of forming the polymer layer **98** as shown in FIGS. **15**I-**15**J can be referred to as the process of forming the polymer layer **95** as illustrated in FIGS. **15**C-**15**H. The process of forming the adhesion/barrier/seed layer **8021** as shown in FIGS. **15**I-**15**J can be referred to as the process of forming the adhesion/barrier/seed layer **8011** as illustrated in FIGS. **15**C-**15**H. The process of forming the bulk metal layer **8022** as shown in FIGS. **15**I-**15**J can be referred to as the process of forming the bulk metal layer **8012** as illustrated in FIGS. **15**C-**15**H. The process illustrated in FIGS. **15**I and **15**J can be repeated for forming one ore more polymer layer and one or more patterned circuit layer over the patterned circuit layer **802** and over the polymer layer **98**.

[0460] Referring to FIG. **15**K, after removing the adhesion/barrier/seed layer **8021** not under the bulk metal layer **8022** as illustrated in FIG. **15**J, a polymer layer **99** can be formed on the bulk metal layer **8022** of the patterned circuit layer **802** and on the polymer layer **98** not covered by the patterned circuit layer **802**. Multiple openings **990** (only one of them shown) in the polymer layer **99** can be over multiple contact points **8000** (only one of them shown) of the bulk metal layer **8022** of the patterned circuit layer **802** and expose the contact points **8000**. In some applications, for example, in the gold over-passivation metal system used for the topmost patterned circuit layer **802**, the polymer layer **99** may optionally be omitted. An over-passivation scheme **102** shown in FIG. **15**K includes the polymer layers **95**, **98** and **99**, and the patterned circuit layers **801** and **802**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the openings **980** in the polymer layer **98** are over the patterned circuit layer **801**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **802** and exposes it.

[0461] After forming the over-passivation scheme **102** of the top post-passivation technology shown in FIG. **15**K, the

semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. The contact points **8000** of the semiconductor chip cut from the semiconductor wafer **10** can be used for connecting to an external circuit by (1) wires (such as gold wires, aluminum wires or copper wires) of a wirebonding process; (2) bumps (such as gold bumps, copper bumps, solder bumps, nickel bumps or other metal bumps) on the other substrates (such as silicon chips, silicon substrates, ceramic substrates, organic substrates, BGA substrates, flexible substrates, flexible tapes or glass substrates). The bumps on the substrates have a height larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 20 micrometers; (3) posts (such as gold posts, copper posts, solder posts, nickel posts or other metal posts) on the other substrates (such as silicon chips, silicon substrates, ceramic substrates, organic substrates, BGA substrates, flexible substrates, flexible tapes or glass substrates). The posts on the substrates have a height larger than 10 micrometers, such as between 10 and 200 micrometers, and preferably between 30 and 120 micrometers; (4) bumps (such as gold bumps, copper bumps, solder bumps, nickel bumps or other metal bumps) on the terminals of metal leads of a lead-frames or a flexible tape. The bumps on the metal leads have a height larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 20 micrometers.

[0462] Alternatively, referring to FIG. **15**L, after forming the structure shown in FIG. **15**K, the contact structure **89** can be formed over the contact point **8000** for connection to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate. The contact structure **89** can be (1) solder pad (with a thickness between 0.1 and 30 micrometers, and preferably between 1 and 10 micrometers) or solder bump (with a height larger than 8 micrometers, such as between 10 and 200 micrometers, and preferably between 30 and 120 micrometers) formed by a suitable process or processes, e.g., by electroplating, or screen printing. A solder reflow process is required to form a ball-shaped solder ball. Solder pad or bump **89** may include high lead solder (PbSn, with Pb composition larger than 85% weight percentage), eutectic solder (PbSn, with ~37% Pb weight percentage, and ~63% Sn weight percentage), lead-free solder including SnAg or SnCuAg, bismuth or indium; (2) gold pads (with a thickness between 0.1 and 10 micrometers, and preferably between 1 and 5 micrometers) or gold bumps (with a height larger than 5 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 20 micrometers) formed by a suitable process or processes, e.g., by electroplating; (3) metal balls formed by a suitable process or processes, e.g., by ball mounting. The metal ball can be a solder ball, a copper ball with surface coating of a Ni layer, or a copper ball with surface coating of a Ni layer and a solder layer, or a copper ball with surface coating of a Ni layer and a gold layer. A diameter of the metal ball is between 10 and 500 micrometers, and preferably between 50 and 300 micrometers. A metal ball can be mounted directly on the contact point **8000** exposed by the polymer opening **990**, or on the metal layer **891**. The metal layer **891** formed for the metal ball mounting may include a composite layer of Ti/Ni, Ti/Cu/Ni, TiW/Ni, TiW/Cu/Ni, Ti/Ni/Au, Ti/Cu/Ni/Au, TiW/Ni/Au, TiW/Cu/Ni/Au, Ti/Cu/Ni/Pd, TiW/Cu/Ni/Pd, Cr/CrCu, NiV/Cu, NiV/Cu, NiV/Au, Ni/Au, Ni/Pd, all layers are from bottom to top. After the metal ball mounting, a solder reflow process is usually required. After forming the contact structure **89**, the wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process for packaging or assembly to connect to external circuits. The assembly methods can be wirebonding (to pads on external organic, ceramic, glass, or silicon substrates, or to leads of a leadframe or a flexible tape), TAB bonding, tape-chip-carrier packaging (TCP), chip-on-glass (COG), chip-on-board (COB), chip-on-film (COF), flip chip on a BGA substrate, chip-on-flex, chip-on-chip stack interconnection or chip-on-Si-substrate stack interconnection.

[0463] An over-passivation scheme **102** shown in FIG. **15**L includes the polymer layers **95**, **98** and **99**, the patterned circuit layers **801** and **802**, and the contact structure **89**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the openings **980** in the polymer layer **98** are over the patterned circuit layer **801**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **802**, and the contact structure **89** is in the opening **990**, on the contact point **8000** and on the polymer layer **99**.

[0464] FIG. **15**M is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, after the steps illustrated in FIG. **15**A and **15**C-**15**H, the polymer layer **98** is formed on the polymer layer **95** and on the bulk metal layer **8012** of the patterned circuit layer **801**, and multiple openings **980** in the polymer layer **98** are over multiple regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** and expose them. Next, a metal layer **89***a* can be formed on the polymer layer **98** and on the regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**. Next, a metal layer **89***b* can be formed on the metal layer **89***a*. The material of the metal layer **89***a* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the metal layer **89***b* may include copper, nickel, aluminum, gold, silver, platinum or palladium. The metal layers **89***a* and **89***b* may be formed by a suitable process or processes, e.g., by a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The metal layer **89***a* may have a thickness smaller than **1** micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, and the metal layer **89***b* may have a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers.

[0465] For example, when the metal layer **89***a* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **98** and on the regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**, the metal layer **89***b* can be formed by a suitable

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process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0466] Alternatively, when the metal layer **89***a* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **98** and on the regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**, the metal layer **89***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0467] Alternatively, when the metal layer **89***a* is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **98** and on the regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**, the metal layer **89***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0468] After forming the metal layer **89***b,* a photoresist layer can be formed on the metal layer **89***b,* and multiple openings in the photoresist layer are over the regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980** and expose the metal layer **89***b.* Next, a metal layer **89***c* can be formed on the metal layer **89***b* exposed by the openings in the photoresist layer by a process including an electroplating process. The metal layer **89***c* may have a thickness larger than 3 micrometer, such as between 3 and 200 micrometers, and preferably between 5 and 100 micrometers, and larger than that of the metal layer **89***b,* that of the metal layer **89***a* and that of each of the fine-line metal layers **60**, respectively. The metal layer **89***c* may have a width larger than 1 micrometer, such as between 5 and 200 micrometers, and preferably between 5 and 50 micrometers, and larger than that of each of the fine-line metal layers **60**. The metal layer **89***c* may include copper, gold, nickel, aluminum, silver, platinum, solder or a composite of the previously described materials.

[0469] For example, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 3 micrometers, such as between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, on the metal layer **89***b,* preferably the previously described copper layer **89***b,* exposed by the openings in the photoresist layer.

[0470] Alternatively, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the metal layer **89***b,* preferably the previously described gold layer **89***b,* exposed by the openings in the photoresist layer.

[0471] Alternatively, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the metal layer **89***b,* preferably the previously described copper layer or nickel layer **89***b,* exposed by the openings in the photoresist layer.

[0472] Alternatively, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness larger than 5 micrometers, such as between 5 and 200 micrometers, and preferably between 10 and 150 micrometers, on the metal layer **89***b,* preferably the previously described copper layer or nickel layer **89***b,* exposed by the openings in the photoresist layer.

[0473] Alternatively, the metal layer **89***c* can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 1 micrometer, such as between 3 and 150 micrometers, and preferably between 5 and 100 micrometers, on the metal layer **89***b,* preferably the previously described copper layer **89***b,* exposed by the openings in the photoresist layer, next electroplating or electroless plating a nickel layer, to a thickness larger than 1 micrometer, such as between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer in the openings in the photoresist layer, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness larger than 0.005 micrometers, such as between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, on the electroplated or electroless plated nickel layer in the openings in the photoresist layer.

[0474] Alternatively, the metal layer **89***c* can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 1 micrometer, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the metal layer **89***b,* preferably the previously described copper layer **89***b,* exposed by the openings in the photoresist layer, next electroplating or electroless plating a nickel layer, to a thickness larger than 1 micrometer, such as between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer in the openings in the photoresist layer, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy,

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to a thickness larger than 1 micrometer, such as between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, on the electroplated or electroless plated nickel layer in the openings in the photoresist layer.

[0475] After forming the metal layer **89***c*, the photoresist layer is removed using an inorganic solution or using an organic solution with amide. Next, the metal layer **89***b* not under the metal layer **89***c* is removed by an etching process, and then the metal layer **89***a* not under the metal layer **89***c* is removed by an etching process. The process of removing the metal layer **89***b* not under the metal layer **89***c* as shown in FIG. **15**M can be referred to as the process of removing the seed layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** as illustrated in FIG. **15**H. The process of removing the metal layer **89***a* not under the metal layer **89***c* as shown in FIG. **15**M can be referred to as the process of etching the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** as illustrated in FIG. **15**H.

[0476] Accordingly, the metal bumps **89** provided by the metal layers **89***a*, **89***b* and **89***c* can be formed on the polymer layer **98** and on the regions **801***a* of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**. The metal layer **89***c* of the metal bumps **89** can be used to be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by bonding the metal layer **89***c* with the external circuit. After removing the metal layer **89***a* not under the metal layer **89***c*, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0477] An over-passivation scheme **102** shown in FIG. **15**M includes the polymer layers **95** and **98**, the patterned circuit layer **801** and the metal bumps **89**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the openings **980** in the polymer layer **98** are over the contact points **801***a* of the patterned circuit layer **801**, and the metal bumps **89** are in the openings **980**, on the contact points **801***a* and on the polymer layer **98**.

[0478] The emboss process shown in FIGS. **15**C to **15**K describes a metal layer is formed by a suitable process or processes, e.g., by only one photoresist patterning process for electroplating a metal layer in an opening in the only one photoresist layer. This type of process is a single-emboss process that means the process includes one and only one photolithography process before removing the adhesion/barrier/seed layer not under the electroplated metal layer. A double-emboss process can be implemented to form a metal trace and a via plug on the metal trace by electroplating metal layers with different patterns using only one adhesion/barrier/seed layer, while performing two photolithography processes, before removing the adhesion/barrier/seed layer not under an electroplated metal layer. The first photolithography process is performed for defining the pattern of the metal trace, while the second photolithography process is performed for defining the pattern of the via plug. FIGS. **15**C-**15**G and FIGS. **16**A-**16**D show a double-embossing process to form an over-passivation scheme over the wafer **10** shown in FIG. **15**A or FIG. **15**B. The double-embossing process has front steps same as the steps shown in FIGS. **15**C-**15**G. The steps of FIGS. **16**A-**16**D follow the steps of FIGS. **15**C-**15**G for a double embossing process. In FIG. **15**G, the photoresist layer **71** is stripped, leaving the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** exposed to the ambient. FIGS. **16**A-**16**M show an example to form an over-passivation scheme for all embodiments in this disclosure by using a double-embossing process to form the metal layer **801** and the via plugs **898**, using a single embossing to form the metal layer **802**, and using a single embossing to form the metal bump **89**.

[0479] Referring to FIG. **16**A, a first photolithography and electroplating process is performed to form the first metal layer **801**, which can be referred to as the step illustrated in FIGS. **15**D-**15**G, and then a second photoresist layer **72** is deposited and patterned on the seed layer of the adhesion/barrier/seed layer **8011** and on the bulk metal layer **8012**. It is noted that openings **720** in the photoresist layer **72** expose the bulk metal layer **8012**; openings **720'** in the photoresist layer **72** expose the seed layer of the adhesion/barrier/seed layer **8011**.

[0480] For example, the photoresist layer **72** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer on the seed layer of the adhesion/barrier/seed layer **8011** and on the electroplated bulk metal layer **8012**, then exposing the photosensitive polymer layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photosensitive polymer layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photosensitive polymer layer, then developing the exposed polymer layer, and then removing the residual polymeric material or other contaminants from the seed layer and form the bulk metal layer **8012** with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the photoresist layer **72** can be patterned with the openings **720** and **720'** exposing the bulk metal layer **8012** and the seed layer of the adhesion/barrier/seed layer **8011**, respectively.

[0481] Referring to FIG. **16**B, since the seed layer of the adhesion/barrier/seed layer **8011** is not removed, a second electroplating process can be performed to form via plugs **898**. Note that a metal piece **898'**on the seed layer of the adhesion/barrier/seed layer **8011** is also formed at a horizontal level lower than via plugs **898**. The metal piece **898'** can be used for packaging purposes. The metal piece **898'** may be thinner or thicker than the bulk metal layer **8012**. It can be used for higher density interconnection (in case of thinner) or used for lower resistance interconnection (in case of thicker).

[0482] The material of the via plug **898** and metal piece **898'** may be gold or copper. For example, the via plug **898** and metal piece **898'** may be formed by a suitable process or processes, e.g., by electroplating a gold layer with a thickness of between 1 and 100 μm, and preferably of between 2 and 30 μm, on the gold layer, exposed by the openings **720**, of the bulk metal layer **8012**, and on the seed layer, made of gold, of the adhesion/barrier/seed layer **8011** exposed by the openings **720'**. Alternatively, the via plug **898** and metal piece **898'** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 1 and 100 μm, and preferably of between 2 and 30 μm, on the copper layer, exposed by the openings **720**, of the bulk metal layer

8012, and on the seed layer, made of copper, of the adhesion/barrier/seed layer **8011** exposed by the openings **720'**.

[0483] Referring to FIG. **16**C, the second photoresist **72** is then removed using an organic solution with amide, exposing the via plugs **898**, the bulk metal layer **8012** not under the via plugs **898**, the seed layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012**, and the metal piece **898'**. However, some residuals from the photoresist layer **72** could remain on the bulk metal layer **8012** and on the seed layer of the adhesion/barrier/seed layer **8011**. Thereafter, the residuals can be removed from the seed layer of the adhesion/barrier/seed layer **8011** and from the bulk metal layer **8012** with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen.

[0484] Referring to FIG. **16**D, the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** and not under the metal piece **898'** is removed by wet and/or dry etching. In the case of wet etching to remove the bottom metal layer **8011** not under the electroplated metal layer **8012** and not under the electroplated metal layer **898**, an undercut **8011'** with a sidewall of the bottom metal layer **8011** recessed from a sidewall of the electroplated metal layer **8012** and with a sidewall of the bottom metal layer **8011** recessed from a sidewall of the electroplated metal layer **898'** is formed. No undercut **8011'** exists when an anisotropies dry etching is used to remove the bottom metal layer **8011** not under the electroplated metal layer **8012** and not under the electroplated metal layer **898'**.

[0485] For example, when the seed layer of the adhesion/barrier/seed layer **8011** is a gold layer, it can be etched with an iodine-containing solution, such as solution containing potassium iodide, with an ion milling process or with an Ar sputtering etching process. Alternatively, when the seed layer of the adhesion/barrier/seed layer **8011** is a copper layer, it can be etched with a solution containing NH_4OH or with an Ar sputtering etching process.

[0486] For example, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide, with a chlorine-containing plasma etching process or with an RIE process. Alternatively, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is a titanium layer, it can be etched with a solution containing hydrogen fluoride, with a chlorine-containing plasma etching process or with an RIE process. Alternatively, when the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** is a chromium layer, it can be etched with a solution containing potassium ferricyanide.

[0487] Referring to FIG. **16**E, a second polymer layer **98** is deposited on the via plugs **898**, on the metal pieces **898'**, on the metal layer **801** and on the exposed first polymer layer **95**. The second polymer layer **98** can be formed by a suitable process or processes, e.g., by a spin-on coating process, a lamination process or a screen-printing process.

[0488] For example, the polymer layer **98** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness of between 6 and 50 μm on the via plugs **898**, on the metal pieces **898'**, on the bulk metal layer **8012** and on the exposed polymer layer **95**, then baking the spin-on coated polyimide layer, and then curing or heating the baked polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness of between 3 and 25 μm. Alternatively, the baked polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient.

[0489] Referring to FIG. **16**F, a polishing or mechanical polishing process, and preferably a chemical-mechanical polishing (CMP) process, is used to planarize the surface of the second polymer layer **98**, exposing the via plugs **898**. The polymer layer **98**, after being planarized, may have a thickness t between 5 and 50 micrometers.

[0490] FIGS. **16**G-**16**K show process steps to form a second over-passivation metal layer **802** using a single-embossing process same as described in FIGS. **15**D-**15**H, that is, an adhesion/barrier/seed layer **8021** is formed, exemplary by sputtering, on the second polymer layer **98** and on the exposed via plugs **898**, followed by forming a photoresist layer **73** on the adhesion/barrier/seed layer **8021**, openings **730** in the photoresist layer **73** exposing the seed layer of the adhesion/barrier/seed layer **8021**, followed by forming a bulk conduction metal layer **8022** on the seed layer exposed by the openings **730**, followed by removing the photoresist layer **73**, followed by removing the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022**. The specification of the adhesion/barrier/seed layer **8021** and the bulk conduction metal layer **8022** shown in FIGS. **16**G-**16**K can be referred to as the specification of the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012** illustrated in FIGS. **15**D-**15**K, respectively. The process of forming the adhesion/barrier/seed layer **8021** shown in FIGS. **16**G-**16**K can be referred to as the process of forming the adhesion/barrier/seed layer **8011** illustrated in FIGS. **15**D-**15**K. The process of forming the bulk conduction metal layer **8022** shown in FIGS. **16**G-**16**K can be referred to as the process of forming the bulk metal layer **8012** illustrated in FIGS. **15**D-**15**K.

[0491] Referring to FIG. **16**L, a polymer layer **99** is then formed and patterned to complete a two-metal-layer over-passivation scheme. An over-passivation scheme **102** shown in FIG. **16**L includes the polymer layers **95**, **98** and **99**, the patterned circuit layers **801** and **802**, the via plugs **898**, and the metal piece **898'**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **802** and exposes it. After the step illustrated in FIG. **16**L, the semiconductor wafer **10** can be optionally cut into a plurality of individual semiconductor chip by a die-sawing process.

[0492] Alternatively, referring to FIG. **16**M, after the step illustrated in FIG. **16**L, the contact structure **89** illustrated in FIG. **15**L or FIG. **15**M can be formed on the exposed contact point **8000** for assembly and/or packaging purposes. The specification of the contact structure **89** shown in FIG. **16**M can be referred to as the specification of the contact structure **89** illustrated in FIG. **15**L or FIG. **15**M. The process of forming the contact structure **89** as shown in FIG. **16**M can be referred to as the process of forming the contact structure **89** illustrated in FIG. **15**L or FIG. **15**M. As an alternative, the double-emboss process steps in FIGS. **15**D-**15**G and **16**A-**16**D for forming the first metal layer **801** and the first via plug **898** can be repeated to form additional metal layer (not shown) on the polymer layer **98** and on the via plugs **898**, and to form additional via plug (not shown) on the additional metal layer. In this alternative, the additional via plug can be

joined with a wirebonded wire using a wirebonding process, with a solder bump using a ball-mounting process or with a flexible substrate using a TAB process. The description and specification in FIGS. **16**A-**16**M can be applied to forming the thick and wide power metal trace, bus or plane **81** over the passivation layer **5** in the disclosure, to forming the thick and wide ground metal trace, bus or plane **82** over the passivation layer **5** in the disclosure, to forming the thick and wide power metal trace, bus or plane **81**P over the passivation layer **5** in the disclosure, and to forming the thick and wide signal metal trace, bus or plane **83**, **83'** or **85** over the passivation layer **5** in the disclosure.

[0493] After forming the over-passivation scheme of the top post-passivation technology shown in FIG. **16**M, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. An over-passivation scheme **102** shown in FIG. **16**M includes the polymer layers **95**, **98** and **99**, the patterned circuit layers **801** and **802**, the via plugs **898**, the metal piece **898'**, and the metal bump **89**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **802**, and the metal bump **89** is in the opening **990**, on the contact point **8000** and on the polymer layer **99**.

[0494] FIGS. **17**A to **17**J show process steps to form an over-passivation scheme **102** with three metal layers **801**, **802** and **803**. Metal layers **801** and **802** are formed by a suitable process or processes, e.g., by a double-emboss process, while the metal layer **803** is formed by a suitable process or processes, e.g., by a single-emboss process. A first double-embossing process is used to form the first metal layer **801** and the first via plug **898** as described in FIGS. **15**D-**15**G and **16**A-**16**D. A first inter-metal polymer layer **98** is formed and planarized to expose the first via plugs **898**, shown in process steps of FIGS. **16**E-**16**F. FIG. **17**A is at the same step as FIG. **16**J when the first metal layer **801**, the first via plugs **898** and the metal piece **898'** are formed by a suitable process or processes, e.g., by a double-emboss metal process, and the inter-metal dielectric polymer layer **98** is formed with the first via plugs **898** being exposed. The design of the first metal layer **801** and the first via plugs **898** in FIG. **17**A is slightly different from that in FIG. **16**J to accommodate an additional metal layer. The process for forming the bottom metal layer **8021** in FIG. **17**A can be referred to as the process for forming the bottom metal layer **8011** in FIG. **15**D or the bottom metal layer **8021** in FIG. **16**G; the process for forming the metal layer **8022** in FIG. **17**A can be referred to as the process for forming the metal layer **8012** in FIG. **15**E or the metal layer **8022** in FIGS. **16**H-**16**J. The specification of the adhesion/barrier/seed layer **8021** and the bulk conduction metal layer **8022** shown in FIGS. **17**A-**17**J can be referred to as the specification of the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012**, respectively, illustrated in FIGS. **15**D-**15**K.

[0495] Referring to FIG. **17**B now, a second photoresist layer **74** is then deposited and patterned to form openings **740** over the bulk conduction metal layer **8022** and/or to optionally form openings **740'** directly on the seed layer of the second adhesion/barrier/seed layer **8021**.

[0496] For example, the photoresist layer **74** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer on the seed layer of the adhesion/barrier/seed layer **8021** and on the bulk conduction metal layer **8022**, then exposing the photosensitive polymer layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photosensitive polymer layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photosensitive polymer layer, then developing the exposed polymer layer, and then removing the residual polymeric material or other contaminants from the seed layer and form the bulk conduction metal layer **8022** with an O_2 plasma or a plasma containing fluorine of below 200PPM and oxygen, such that the photoresist layer **74** can be patterned with the openings **740** and **740'** exposing the bulk conduction metal layer **8022** and the seed layer of the adhesion/barrier/seed layer **8021**, respectively.

[0497] Referring to FIG. **17**C, a second via plug layer is electroplated in the photoresist openings **740** and **740'** to form the second via plugs **897** and the second metal piece **897'**. The second metal piece **897'** can be used as described for the first metal piece **989'**. The material of the via plug **897** and metal piece **897'** may be gold or copper. For example, the via plug **897** and metal piece **897'** may be formed by a suitable process or processes, e.g., by electroplating a gold layer with a thickness of between 1 and 100 μm, and preferably of between 2 and 30 μm, on the gold layer, exposed by the openings **740**, of the bulk conduction metal layer **8022**, and on the seed layer, made of gold, of the adhesion/barrier/seed layer **8021** exposed by the openings **740'**. Alternatively, the via plug **897** and metal piece **897'** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 1 and 100 μm, and preferably of between 2 and 30 μm, on the copper layer, exposed by the openings **740**, of the bulk conduction metal layer **8022**, and on the seed layer, made of copper, of the adhesion/barrier/seed layer **8021** exposed by the openings **740'**.

[0498] Referring to FIG. **17**D, the second photoresist layer **74** is then stripped using an organic solution with amide. However, some residuals from the photoresist layer **74** could remain on the bulk conduction metal layer **8022** and on the seed layer of the adhesion/barrier/seed layer **8021**. Thereafter, the residuals can be removed from the bulk conduction metal layer **8022** and from the seed layer with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen.

[0499] Alternatively, after the bulk conduction metal layer **8022** is formed on the seed layer of the adhesion/barrier/seed layer **8021** exposed by the openings **730** illustrated in FIG. **16**I, without removing the photoresist layer **73**, the photoresist layer **74** shown in FIG. **17**B can be formed on the photoresist layer **73** and on the bulk conduction metal layer **8022**. The openings **740** in the photoresist layer **74** expose the bulk conduction metal layer **8022**, respectively, for defining the pattern of the via plugs **897**. The process for forming the via plugs **897** can be referred to as the above disclosure. Finally, the photoresist layers **73** and **74** are removed using an organic solution with amide. However, some residuals from the photoresist layers **73** and **74** could remain on the bulk conduction metal layer **8022**, on the via plugs **897** and on the seed layer of the adhesion/barrier/seed layer **8021**. Thereafter, the residuals can be removed from the seed layer of the adhesion/barrier/seed layer **8021**, from the via plugs **897** and from, the

bulk conduction metal layer **8022** with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen. Next, the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022** can be removed, as mentioned in the above description.

[0500] Referring to FIG. **17**E, the second adhesion/barrier/seed layer **8021** not under the second bulk conduction metal layer **8022** and not under the second metal piece **987'** is removed. The process of removing the second adhesion/barrier/seed layer **8021** not under the second bulk conduction metal layer **8022** and not under the second metal piece **897'**, as shown in FIG. **17**E, can be referred to as the process of removing the first adhesion/barrier/seed layer **8011** not under the first bulk metal layer **8012** and not under the metal piece **898'**, as illustrated in FIG. **16**D.

[0501] Referring to FIGS. **17**F-**17**G, a second inter-metal dielectric polymer layer **97** is then deposited and planarized to expose the second via plugs **897**. The material of the polymer layer **97** may be polyimide (PI), benzocyclobutane (BCB), polyurethane, epoxy resin, a parylene-based polymer, a solder-mask material, an elastomer, silicone or a porous dielectric material. The process for forming the polymer layer **97** in FIG. **17**F can be as referred to as the process for forming the polymer layer **98** in FIG. **16**E; the process for planarizing the polymer layer **97** in FIG. **17**G can be as referred to as the process for planarizing the polymer layer **98** in FIG. **16**F.

[0502] For example, the polymer layer **97** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness of between 10 and 120 μm on the exposed bulk conduction metal layer **8022**, on the via plugs **897**, on the metal piece **897'** and on the exposed polymer layer **98**, then baking the spin-on coated polyimide layer, then curing or heating the baked polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness of between 5 and 60 μm, and then polishing or mechanical polishing, exemplary chemical-mechanical polishing, an upper surface of the polymer layer **97** to uncover the via plugs **897** and to planarize the upper surface thereof. Alternatively, the baked polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient.

[0503] FIGS. **17**H and **17**I show a single-embossing process is used to form a third metal layer **803** by first depositing an adhesion/barrier/seed layer **8031**, depositing and patterning a photoresist layer, electroplating a bulk conduction metal layer **8032**, stripping the photoresist layer and self-aligned etch the adhesion/barrier/seed layer **8031**. The specification of the adhesion/barrier/seed layer **8031** and the bulk conduction metal layer **8032** shown in FIGS. **17**H-**17**I can be referred to as the specification of the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012**, respectively, illustrated in FIGS. **15**D-**15**H. The process of forming the adhesion/barrier/seed layer **8031** shown in FIGS. **17**H-**17**I can be referred to as the process of forming the adhesion/barrier/seed layer **8011** illustrated in FIGS. **15**D-**15**H. The process of forming the bulk conduction metal layer **8032** shown in FIGS. **17**H-**17**I can be referred to as the process of forming the bulk metal layer **8012** illustrated in FIGS. **15**D-**15**H.

[0504] FIG. **17**J shows a completed structure by forming a polymer layer **99** on the exposed polymer layer **97** and on the third metal layer **803**, and an opening **990** in the polymer layer **99** exposes a contact point **8000** for interconnection to an external circuit. The polymer layer **99** may be formed by a suitable process or processes, e.g., by a spin-on coating process, a lamination process or a screen-printing process. The polymer layer **99** may include polyimide (PI), benzocyclobutane (BCB), polyurethane, epoxy resin, a parylene-based polymer, a solder-mask material, an elastomer, silicone or a porous dielectric material.

[0505] For example, the polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness of between 6 and 50 μm on the exposed polymer layer **97** and on the bulk conduction metal layer **8032**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form a polyimide opening in the exposed polyimide layer exposing the contact point **8000**, then curing or heating the developed polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness of between 3 and 25 μm, and then removing the residual polymeric material or other contaminants from the contact point **8000** exposed by the polyimide opening with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the polymer layer **99** can be patterned with an opening **990** in the polymer layer **99** exposing the contact point **8000**. Alternatively, the developed polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient.

[0506] The contact point **8000** can be used to be connected to an external circuit via a wirebonding process, a solder bonding process or a tape-automated-bonding (TAB) process, and the external circuit may be another semiconductor chip, a flexible substrate including a polymer layer (such as polyimide) having a thickness between 30 and 200 micrometers and not including any polymer layer with glass fiber, a glass substrate, a ceramic substrate including a ceramic material as insulating layers between circuit layers, a silicon substrate, an organic substrate, a printed circuit board (PCB) or a ball grid array (BGA) substrate.

[0507] After forming the over-passivation scheme of the top post-passivation technology shown in FIG. **17**J, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. An over-passivation scheme **102** shown in FIG. **17**J includes the polymer layers **95**, **97**, **98** and **99**, the patterned circuit layers **801**, **802** and **803**, the via plugs **897** and **898**, and the metal pieces **897'** and **898'**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the opening **990** in

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the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **803** and exposes it.

[0508] FIGS. **18**A to **18**I show another alternative of process steps to form an over-passivation scheme with three metal layers **801**, **802** and **803**. Metal layers **801** and **803** are formed by a suitable process or processes, e.g., by a single-emboss process, while the metal layer **802** is formed by a suitable process or processes, e.g., by a double-emboss process.

[0509] Referring to FIG. **18**A, a first single-embossing process is used to form the first metal layer **801** as described in FIGS. **15**D-**15**H. Next, a first inter-metal polymer layer **98** is deposited and patterned with openings **980** to expose the first metal layer **801**, as shown in process step of FIG. **15**I. FIG. **18**A is at the same process step as FIG. **15**I when the first metal layer **801** and the first inter-metal dielectric polymer layer **98** are formed by a suitable process or processes, e.g., by a single-emboss metal process, and the inter-metal dielectric polymer layer **98** is deposited and patterned with openings **980** exposing the first metal layer **801**. The design of the first metal layer **801** and the first inter-metal polymer openings **980** in FIG. **18**A is slightly different from that in FIG. **15**I to accommodate an additional metal layer. The process steps in FIGS. **18**B-**18**G show a double-embossing process to form a second metal layer **802** and via plugs **897**. The specification of the polymer layer **95**, the metal layer **801** and the polymer layer **98** shown in FIGS. **18**A-**18**I can be referred to as the specification of the polymer layer **95**, the metal layer **801** and the polymer layer **98**, respectively, illustrated in FIGS. **15**C-**15**K. The process of forming the polymer layer **95** shown in FIG. **18**A can be referred to as the polymer layer **95** illustrated in FIGS. **15**C-**15**K. The process of forming the metal layer **801** shown in FIG. **18**A can be referred to as the metal layer **801** illustrated in FIGS. **15**C-**15**K. The process of forming the polymer layer **98** shown in FIG. **18**A can be referred to as the polymer layer **98** illustrated in FIGS. **15**C-**15**K.

[0510] Referring to FIG. **18**B, a second adhesion/barrier/seed layer **8021** is deposited on the polymer layer **98** and on the first metal layer **801** exposed by the openings **980**. The specification of the second adhesion/barrier/seed layer **8021** shown in FIGS. **18**B-**18**I can be referred to as the specification of the second adhesion/barrier/seed layer **8021** illustrated in FIGS. **15**J-**15**K. The process of forming the second adhesion/barrier/seed layer **8021** shown in FIG. **18**B can be referred to as the process of forming the second adhesion/barrier/seed layer **8021** illustrated in FIGS. **15**J-**15**K.

[0511] Referring to FIG. **18**C, a photoresist layer **73**, such as positive-type photoresist layer, is deposited on the seed layer of the second adhesion/barrier/seed layer **8021**. Next, the photoresist layer **73** is patterned with exposure and development processes to form openings **730** in the photoresist layer **73** exposing the seed layer of the second adhesion/barrier/seed layer **8021**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **73** during the process of exposure.

[0512] For example, the photoresist layer **73** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer on the seed layer of the second adhesion/barrier/seed layer **8021**, then exposing the photosensitive polymer layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photosensitive polymer layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photosensitive polymer layer, then developing the exposed polymer layer, and then removing the residual polymeric material or other contaminants from the seed layer with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the photoresist layer **73** can be patterned with openings **730** in the photoresist layer **73** exposing the seed layer.

[0513] Next, a bulk conduction layer **8022** can be electroplated and/or electroless plated over the seed layer exposed by the openings **730**. The bulk conduction layer **8022** may be a single layer of gold, copper, silver, palladium, platinum, rhodium, ruthenium, rhenium or nickel, or a composite layer made of the previously described metals. The specification of the bulk conduction metal layer **8022** shown in FIGS. **18**C-**18**I can be referred to as the specification of the bulk metal layer **8012** illustrated in FIGS. **15**F-**15**K. The process of forming the bulk conduction metal layer **8022** shown in FIGS. **18**C-**18**I can be referred to as the process of forming the bulk metal layer **8012** illustrated in FIGS. **15**F-**15**K.

[0514] Referring to FIG. **18**D, the photoresist layer **73** is then stripped using an organic solution with amide. However, some residuals from the photoresist layer **73** could remain on the bulk conduction metal layer **8022** and on the seed layer of the adhesion/barrier/seed layer **8021**. Thereafter, the residuals can be removed from the seed layer of the adhesion/barrier/seed layer **8021** and from the bulk conduction metal layer **8022** with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen.

[0515] Referring to FIG. **18**E, a photoresist layer **74** is then deposited and patterned to form openings **740** over the second bulk conduction metal layer **8022** and/or to optionally form openings **740'** directly on the seed layer of the second adhesion/barrier/seed layer **8021**. For example, the photoresist layer **74** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer on the seed layer of the adhesion/barrier/seed layer **8021** and on the bulk conduction metal layer **8022**, then exposing the photosensitive polymer layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the photosensitive polymer layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the photosensitive polymer layer, then developing the exposed polymer layer, and then removing the residual polymeric material or other contaminants from the seed layer and form the bulk conduction metal layer **8022** with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the photoresist layer **74** can be patterned with the openings **740** and **740'** exposing the bulk conduction metal layer **8022** and the seed layer of the adhesion/barrier/seed layer **8021**, respectively.

[0516] Next, a via plug layer is electroplated in the photoresist openings **740** and **740'** to form via plugs **897** and metal piece **897'**. The metal piece **897'** can be used as described for the metal piece **898'** in FIG. **16**D.

[0517] The material of the via plug **897** and metal piece **897'** may be gold or copper. For example, the via plug **897** and metal piece **897'** may be formed by a suitable process or processes, e.g., by electroplating a gold layer with a thickness

of between 1 and 100 μm, and preferably of between 2 and 30 μm, on the gold layer, exposed by the openings **740**, of the bulk conduction metal layer **8022**, and on the seed layer, made of gold, of the adhesion/barrier/seed layer **8021** exposed by the openings **740'**. Alternatively, the via plug **897** and metal piece **897'** may be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness of between 1 and 100 μm, and preferably of between 2 and 30 μm, on the copper layer, exposed by the openings **740**, of the bulk conduction metal layer **8022**, and on the seed layer, made of copper, of the adhesion/barrier/seed layer **8021** exposed by the openings **740'**.

[0518] Referring to FIG. **18**F, the photoresist layer **74** is then stripped using an organic solution with amide. However, some residuals from the photoresist layer **74** could remain on the exposed bulk conduction metal layer **8022**, on the via plugs **897**, on the metal piece **897'** and on the seed layer of the adhesion/barrier/seed layer **8021**. Thereafter, the residuals can be removed from the seed layer, from the via plugs **897**, from the metal piece **897'** and from the bulk conduction metal layer **8022** with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen.

[0519] Alternatively, after the bulk conduction metal layer **8022** is formed on the seed layer of the adhesion/barrier/seed layer **8021** exposed by the openings **730** illustrated in FIG. **18**C, without removing the photoresist layer **73**, the photoresist layer **74** shown in FIG. **18**E can be formed on the photoresist layer **73** and on the bulk conduction metal layer **8022**. The openings **740** in the photoresist layer **74** expose the bulk conduction metal layer **8022**, respectively, for defining the pattern of the via plugs **897**. The process for forming the via plugs **897** can be referred to as the above disclosure. Finally, the photoresist layers **73** and **74** are removed using an organic solution with amide. However, some residuals from the photoresist layers **73** and **74** could remain on the bulk conduction metal layer **8022**, on the via plugs **897** and on the seed layer of the adhesion/barrier/seed layer **8021**. Thereafter, the residuals can be removed from the seed layer of the adhesion/barrier/seed layer **8021**, from the via plugs **897** and from the bulk conduction metal layer **8022** with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen. Next, the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022** can be removed, as mentioned in the above description.

[0520] Referring to FIG. **18**G, the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022** and not under the metal piece **897'** can be removed. The process of removing the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022** and not under the second metal piece **897'**, as shown in FIG. **18**G, can be referred to as the process of removing the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** and not under the metal piece **898'**, as illustrated in FIG. **16**D.

[0521] Referring to FIG. **18**H, a second inter-metal dielectric polymer layer **97** is then deposited and planarized to expose the second via plugs **897**. The material of the polymer layer **97** may be polyimide (PI), benzocyclobutane (BCB), polyurethane, epoxy resin, a parylene-based polymer, a solder-mask material, an elastomer, silicone or a porous dielectric material.

[0522] For example, the polymer layer **97** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness of between 10 and 120 μm on the exposed bulk conduction metal layer **8022**, on the via plugs **897**, on the metal piece **897'** and on the exposed polymer layer **98**, then baking the spin-on coated polyimide layer, then curing or heating the baked polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness of between 5 and 60 μm, and then polishing or mechanical polishing, exemplary chemical-mechanical polishing, an upper surface of the polymer layer **97** to uncover the via plugs **897** and to planarize the upper surface thereof. Alternatively, the baked polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient.

[0523] FIG. **18**I shows a completed structure by first forming the third metal layer **803** is formed by a suitable process or processes, e.g., by a single-embossing process as described in FIGS. **17**H-**17**I. Next, a polymer layer **99** is spin coated on the patterned circuit layer **803**, and an opening **990** is formed in the polymer layer **99** to expose a contact point **8000** for interconnection to an external circuit. The specification of the adhesion/barrier/seed layer **8031** and the bulk conduction metal layer **8032** shown in FIG. **18**I can be referred to as the specification of the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012**, respectively, illustrated in FIGS. **15**D-**15**H. The process of forming the adhesion/barrier/seed layer **8031** shown in FIG. **18**I can be referred to as the process of forming the adhesion/barrier/seed layer **8011** illustrated in FIGS. **15**D-**15**H. The process of forming the bulk conduction metal layer **8032** shown in FIG. **18**I can be referred to as the process of forming the bulk metal layer **8012** illustrated in FIGS. **15**D-**15**H. The specification of the polymer layer **99** shown in FIG. **18**I can be referred to as the specification of the polymer layer **99** illustrated in FIG. **17**J. The process of forming the polymer layer **99** shown in FIG. **18**I can be referred to as the process of forming the polymer layer **99** and the opening **990** illustrated in FIG. **17**J.

[0524] The contact point **8000** can be used to be connected to an external circuit via a wirebonding process, a solder bonding process or a tape-automated-bonding (TAB) process, and the external circuit may be another semiconductor chip, a flexible substrate including a polymer layer (such as polyimide) having a thickness of between 30 and 200 micrometers and not including any polymer layer with glass fiber, a glass substrate, a ceramic substrate including a ceramic material as insulating layers between circuit layers, a silicon substrate, an organic substrate, a printed circuit board (PCB) or a ball grid array (BGA) substrate.

[0525] After forming the over-passivation scheme of the top post-passivation technology shown in FIG. **18**I, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. An over-passivation scheme **102** shown in FIG. **18**I includes the polymer layers **95**, **97**, **98** and **99**, the patterned circuit layers **801**, **802** and **803**, the via plugs **897**, and the metal piece **897'**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the openings **980** in the polymer layer **98** are over the patterned circuit layer **801**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **803** and exposes it.

[0526] FIGS. **19**A to **19**H show another alternative of process steps to form an over-passivation scheme with two metal layers **801** and **802**. The metal layer **801** is formed by a suitable process or processes, e.g., by a double-emboss process, while the metal layer **802** is formed by a suitable process or processes, e.g., by a single-emboss process.

[0527] Referring to FIG. **19**A, after the process steps of FIGS. **15**C-**15**G and **16**A-**16**F for forming the polymer layer **95**, the openings **950**, the metal layer **801**, the via plugs **898**, the metal pieces **898'** and the polymer layer **98** are completed, a polymer layer **97** can be formed on the polymer layer **98**, multiple openings **970** in the polymer layer **97** exposing the via plugs **898**. The material of the polymer layer **97** may be polyimide (PI), benzocyclobutane (BCB), polyurethane, epoxy resin, a parylene-based polymer, a solder-mask material, an elastomer, silicone or a porous dielectric material.

[0528] For example, the polymer layer **97** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness of between 6 and 50 μm on the polymer layer **98** and on the exposed via plugs **898**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form polyimide openings in the exposed polyimide layer exposing the exposed via plugs **898**, then curing or heating the developed polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness of between 3 and 25 μm, and then removing the residual polymeric material or other contaminants from the upper surface of the via plugs **898** exposed by the polyimide openings with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the polymer layer **97** can be patterned with openings **970** exposing the via plugs **898**. Alternatively, the developed polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient. [0051] Referring to FIG. **19**B, an adhesion/barrier/seed layer **8021** is deposited, exemplary by sputtering, on the polymer layer **97** and on the via plugs **898** exposed by the openings **970**. Alternatively, the adhesion/barrier/seed layer **8021** can be formed by a suitable process or processes, e.g., by a process including a vapor deposition method, an evaporation method, a CVD method, an electroless plating method or a PVD method. The specification of the adhesion/barrier/seed layer **8021** shown in FIGS. **19**B-**19**I can be referred to as the specification of the adhesion/barrier/seed layer **8011** illustrated in FIGS. **15**D-**15**K. The process of forming the adhesion/barrier/seed layer **8021** shown in FIG. **19**B can be referred to as the process of forming the adhesion/barrier/seed layer **8011** illustrated in FIGS. **15**D-**15**K.

[0529] Referring to FIG. **19**C, a photoresist layer **73**, such as positive-type photoresist layer, is formed on the adhesion/barrier/seed layer **8021**. Next, the photoresist layer **73** is patterned with exposure and development processes to form openings **730** in the photoresist layer **73** exposing the adhesion/barrier/seed layer **8021**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **730** during the process of exposure. The process of forming the photoresist layer **73** and the openings **730** in the photoresist layer **73** shown in FIG. **19**C can be referred to as the process of forming the photoresist layer **73** and the openings **730** in the photoresist layer **73** illustrated in FIG. **18**C.

[0530] Referring to FIG. **19**D, a bulk conduction metal layer **8022** can be electroplated and/or electroless plated over the adhesion/barrier/seed layer **8021** exposed by the openings **730**. The bulk conduction layer **8022** may be a single layer of gold, copper, silver, palladium, platinum, rhodium, ruthenium, rhenium or nickel, or a composite layer made of the previously described metals. The specification of the bulk conduction metal layer **8022** shown in FIGS. **19**D-**19**I can be referred to as the specification of the bulk metal layer **8012** illustrated in FIGS. **15**F-**15**K. The process of forming the bulk conduction metal layer **8022** shown in FIG. **19**D can be referred to as the process of forming the bulk metal layer **8012** illustrated in FIGS. **15**F-**15**K.

[0531] Referring to FIG. **19**E, after the bulk conduction metal layer **8022** is formed, most of the photoresist layer **73** can be removed using an organic solution with amide. However, some residuals from the photoresist layer **73** could remain on the bulk conduction metal layer **8022** and on the seed layer of the adhesion/barrier/seed layer **8021**. Thereafter, the residuals can be removed from the bulk conduction metal layer **8022** and from the seed layer with a plasma, such as O_2 plasma or plasma containing fluorine of below 200 PPM and oxygen.

[0532] Referring to FIG. **19**F, the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022** is removed with a dry etching method or a wet etching method. As to the wet etching method, when the seed layer of the adhesion/barrier/seed layer **8021** is a gold layer, it can be etched with an iodine-containing solution, such as solution containing potassium iodide; when the seed layer of the adhesion/barrier/seed layer **8021** is a copper layer, it can be etched with a solution containing NH_4OH; when the adhesion/barrier layer of the adhesion/barrier/seed layer **8021** is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide; when the adhesion/barrier layer of the adhesion/barrier/seed layer **8021** is a titanium layer, it can be etched with a solution containing hydrogen fluoride; when the adhesion/barrier layer of the adhesion/barrier/seed layer **8021** is a chromium layer, it can be etched with a solution containing potassium ferricyanide. As to the dry etching method, when the seed layer of the adhesion/barrier/seed layer **8021** is a gold layer, it can be removed with an ion milling process or with an Ar sputtering etching process; when the adhesion/barrier layer of the adhesion/barrier/seed layer **8021** is a titanium layer or a titanium-tungsten-alloy layer, it can be etched with a chlorine-containing plasma etching process or with an RIE process. Generally, the dry etching method to etch the adhesion/barrier/seed layer **8021** not under the bulk conduction metal layer **8022** may include a chemical plasma etching process, a sputtering etching process, such as argon sputter process, or a chemical vapor etching process.

[0533] Accordingly, a second metal layer **802** can be formed on the polymer layer **97** and on the via plugs **898** exposed by the openings **970**, and the second metal layer **802**

is formed with the adhesion/barrier/seed layer **8021** and the bulk conduction metal layer **8022** on the adhesion/barrier/seed layer **8021**.

[0534] Referring to FIG. **19**G, a polymer layer **99** is formed on the exposed polymer layer **97** and on the bulk metal layer **8022** via a spin-on coating process. Referring to FIG. **19**H, the polymer layer **99** is patterned with exposure and development processes to form an opening **990** in the polymer layer **99** exposing the contact point **8000**. Alternatively, the polymer layer **99** may be formed by a suitable process or processes, e.g., by a lamination process or a screen-printing process. The polymer layer **99** may include polyimide (PI), benzocyclobutane (BCB), polyurethane, epoxy resin, a parylene-based polymer, a solder-mask material, an elastomer, silicone or a porous dielectric material.

[0535] For example, the polymer layer **99** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness of between 6 and 50 μm on the exposed polymer layer **97** and on the bulk conduction metal layer **8022**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form an polyimide opening in the exposed polyimide layer exposing the contact point **8000**, then curing or heating the developed polyimide layer at a peak temperature of between 290 and 400° C. for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness of between 3 and 25 μm, and then removing the residual polymeric material or other contaminants from the contact point **8000** exposed by the polyimide opening with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen, such that the polymer layer **99** can be patterned with an opening **990** in the polymer layer **99** exposing the contact point **8000**. Alternatively, the developed polyimide layer can be cured or heated at a temperature between 150 and 290° C., and preferably of between 260 and 280° C., for a time of between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient.

[0536] After forming the over-passivation scheme of the top post-passivation technology shown in FIG. **19**H, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. The method of connecting the contact point **8000** in FIG. **19**H to an external circuit can be referred to as the method of connecting the contact point **8000** in FIG. **15**K to an external circuit. The external circuit may be another semiconductor chip, a flexible substrate including a polymer layer (such as polyimide) having a thickness between 30 and 200 μm and not including any polymer layer with glass fiber, a glass substrate, a ceramic substrate including a ceramic material as insulating layers between circuit layers, a silicon substrate, an organic substrate, a printed circuit board (PCB) or a ball grid array (BGA) substrate. For example, referring to FIG. **19**I, via a wirebonding process, a wire **89'**, such as gold wire, copper wire or aluminum wire, can be bonded to the contact point **8000** of the semiconductor chip cut from the wafer **10**.

[0537] Alternatively, the contact structure **89** illustrated in FIG. **15**L or FIG. **15**M can be formed on the contact point **8000** exposed by the opening **990**. After the contact structure **89** is formed on the contact point **8000** of the wafer **10** shown in FIG. **19**H, the wafer **10** can be diced into a plurality of individual semiconductor chip. An over-passivation scheme **102** shown in FIG. **19**H includes the polymer layers **95**, **97**, **98** and **99**, the patterned circuit layers **801** and **802**, the via plugs **898**, and the metal piece **898'**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the openings **970** in the polymer layer **97** are over the via plugs **898**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **802** and exposes it.

[0538] FIGS. **21** and **22** show top views of a MOS transistor that can be a PMOS transistor or an NMOS transistor. Referring to FIG. **21**, a transistor includes an active region **200**, diffusion region, in or over the silicon substrate **1**, a field oxide region **202** on the silicon substrate **1** and around the active region **200**, a gate **204** on the field oxide region **202** and across the active region **200**, and a gate oxide (not shown) between the active region **200** and the gate **204**. The active region **200** can be defined as a source **206** at a side of the gate **204**, and a drain **208** at the other side of the gate **204**. The material of the gate **204** may be poly silicon, metal silicide or composite layer of above materials, and the metal silicide may be NiSi, CoS, $TiSi_2$ or WSi. Alternatively, the material of the gate **204** may be a metal, such as W, WN, TiN, Ta, TaN, Mo, or alloy or composite layer of above materials. The material of the gate oxide may be silicon oxide or high k oxide, such as Hf containing oxide. The Hf containing oxide may be HfO_2, HfSiON or HfSiO. The previously described physical channel width and physical channel length in the disclosure can be defined in FIG. **21**. The reference mark of W is defined as the physical channel width of the transistor, the length of the gate **204** crossing over the diffusion region **200**; the reference mark of L is defined as the physical channel length of the transistor, the width of the gate **204** over the diffusion region **200**.

[0539] Referring to FIG. **22**, alternatively, a transistor may include a gate **204** with multiple portions $\mathbf{204}_1$-$\mathbf{204}_n$ over one or more diffusion regions **200**. The reference marks of W_1-W_n are defined as the physical channel width of each portion $\mathbf{204}_1$-$\mathbf{204}_n$ of the gate **204**, the length of each portion $\mathbf{204}_1$-$\mathbf{204}_n$ of the gate **204** crossing over the diffusion region **200**; the reference mark of L is defined as the physical channel length of one of the portions $\mathbf{204}_1$-$\mathbf{204}_n$ of the gate **204**, the width of one of the portions $\mathbf{204}_1$-$\mathbf{204}_n$ of the gate **204** over the diffusion region **200**. In this case, the physical channel width W of the transistor is the summation of the physical channel widths W_1-W_n of each portions $\mathbf{204}_1$-$\mathbf{204}_n$ of the gate **204**, and the physical channel length L of the transistor is the physical channel length L of one of the portions $\mathbf{204}_1$-$\mathbf{204}_n$ of the gate **204**.

[0540] FIGS. **23**A-**23**M show cross-sectional views for packaging a DRAM chip using the previously described process, and the elements, shown in FIGS. **23**A-**23**M, indicated by same reference numbers as those indicating the previously described elements can be referred to as the above description about them. Referring to FIG. **23**A, a DRAM wafer **10** includes multiple memory cells (not shown), multiple off-chip circuits and multiple internal circuits **20** in or on the silicon substrate **1**. The DRAM wafer **10** may include an

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electrical fuse **25** and a laser fuse **26** over the silicon substrate **1**, and the electrical fuse **25** and laser fuse **26** are connected to fine-line metal layers **30** over the silicon substrate **1**. The electrical fuse **25** is composed of a polysilicon layer **251** having a thickness between 200 and 2,000 angstroms and a metal-silicide layer **252** having a thickness between 1,000 and 3,000 angstroms on the polysilicon layer **251**. The metal-silicide layer **252** may contain titanium, cobalt, nickel or tungsten. The electrical fuse **25** in an unblown condition may have a sheet resistance of between 1 and 15 ohms/square. There may be an oxide-containing insulating layer having a dielectric constant of less than 3 on and/or under the electrical fuse **25**. The laser fuse **26** may contain copper, aluminum or polysilicon. An opening **526** in the passivation layer **5** is formed over the laser fuse **26** and exposes a silicon-oxide layer over the laser fuse **26**.

[0541] Next, an electrical testing process in a wafer level can be performed to verify good dies, non-repairable bad dies and repairable bad dies. Next, a step of laser repairing the repairable bad dies can be performed. In the step of laser repairing the repairable bad dies, the laser fuse **26** can be blown by laser light, such that the metal traces connected to both ends of the laser fuse **26** becomes an open circuit, as shown in FIG. **23**B. Accordingly, the repairable bad dies possibly turn out to be good dies.

[0542] Next, referring to FIG. **23**C, a polymer layer **95** can be formed on the passivation layer **5**, on the silicon-oxide layer on the laser fuse **26** and on the blown portion of the laser fuse **26**, with multiple openings **950** in the polymer layer **95** exposing multiple contact pads **600**, such as aluminum pads or copper pads, exposed by multiple openings **50** in the passivation layer **5**. The step of forming the polymer layer **95** can be referred to as the step of forming the polymer layer **95** on the passivation layer **5** as shown in FIG. **15**C.

[0543] Next, referring to FIG. **23**D, an adhesion/barrier/seed layer **8011** is formed on the polymer layer **95** and on the contact pads **600**, which can be referred to as the step of forming the adhesion/barrier/seed layer **8011** on the polymer layer **95** and on the contact pads **600** as shown in FIG. **15**D. Next, referring to FIG. **23**E, a photoresist layer **71** is formed on the adhesion/barrier/seed layer **8011**, with multiple openings **710** in the photoresist layer **71** exposing a seed layer of the adhesion/barrier/seed layer **8011**, which can be referred to as the step of forming the photoresist layer **71** on the adhesion/barrier/seed layer **8011** as shown in FIG. **15**E. Next, referring to FIG. **23**F, a bulk conduction layer **8012** is formed over the adhesion/barrier/seed layer **8011** exposed by the openings **710** in the photoresist layer **71**, which can be referred to as the step of forming the bulk conduction layer **8012** on the adhesion/barrier/seed layer **8011** as shown in FIG. **15**F. Next, referring to FIG. **23**G, the photoresist layer **71** is removed from the seed layer of the adhesion/barrier/seed layer **8011**, which can be referred to as the step of removing the photoresist layer **71** as shown in FIG. **15**G. Next, referring to FIG. **23**H, the adhesion/barrier/seed layer **8011** not under the bulk conduction layer **8012** is removed, which can be referred to as the step of removing the adhesion/barrier/seed layer **8011** not under the bulk conduction layer **8012** as shown in FIG. **15**H. Accordingly, the patterned circuit layer **801** can be formed with the adhesion/barrier/seed layer **8011** and the bulk conduction layer **8012** over the adhesion/barrier/seed layer **8011**. The patterned circuit layer **801** may have a left portion connecting multiple of the internal circuits **20**, without being connected to an external circuit through an opening in the polymer layer **99**, and a right portion, for a relocation objective, readily connecting an off-chip circuit **40** to an external circuit through the opening **990** in the polymer layer **99**.

[0544] Next, referring to FIG. **23**I, a polymer layer **99** can be formed on the patterned circuit layer **801** and on the polymer layer **95**, with multiple openings **990** in the polymer layer **99** exposing multiple contact points **8000** of the patterned circuit layer **801**. The step of forming the polymer layer **99** on the patterned circuit layer **801** and on the polymer layer **95** can be referred to as the step of forming the polymer layer **99** on the patterned circuit layer **802** and on the polymer layer **98** as shown in FIG. **15**K. The patterned circuit layer **801** may have a left portion connecting multiple of the internal circuits **20**, without being connected to an external circuit through any opening in the polymer layer **99**, and all of the left portion is covered by the polymer layer **99**, and a right portion, for a relocation objective, readily connecting an off-chip circuit **40** to an external circuit through the opening **990** in the polymer layer **99**.

[0545] Next, referring to FIG. **23**J, another electrical testing process in a wafer level can be optionally performed to verify good dies, non-repairable bad dies and repairable bad dies. Next, a step of E-fuse repairing the repairable bad dies can be performed. In the step of E-fuse repairing the repairable bad dies, an electric current between 0.05 and 2 amperes passes through the electrical fuse **25** for a time between 50 and 1,800 microseconds, and preferably an electric current between 0.1 and 1 amperes passes through the electrical fuse **25** for a time between 100 and 900 microseconds, leading the electrical fuse **25** to be blown. At this time, the electrical fuse **25** has a portion having an electrical current only pass through the polysilicon layer **251** thereof but not pass through the metal-silicide layer **252** thereof. Accordingly, the repairable bad dies possibly turn out to be good dies. The blown electrical fuse **25** may have a sheet resistance between 100 and 10,000 ohms/square. After the step of E-fuse repairing the repairable bad dies, another electrical testing process in a wafer level can be optionally performed to verify good dies, non-repairable bad dies and repairable bad dies.

[0546] Next, the DRAM wafer **10** can be cut into multiple DRAM chips **10'** using a mechanical cutting process or using a laser cutting process, as shown in FIG. **23**K. The non-repairable bad dies can be discarded without being packaged in the following processes. An over-passivation scheme **102** shown in FIG. **23**K includes the patterned circuit layer **801** and the polymer layers **95** and **99**, and the openings **950** in the polymer layer **95** are over the regions of the metal pads or traces **600** exposed by the openings **50** in the passivation layer **5**, and the opening **990** in the polymer layer **99** is over the contact point **8000** of the patterned circuit layer **801** and exposes it.

[0547] Next, referring to FIG. **23**L, one of the DRAM chips **10'** can be mounted to a printed circuit board (PCB) **13**, ball-grid-array (BGA) substrate, via an adhesive material **11**, such as silver epoxy. Next, a wire **89'**, such as gold wire, copper wire or aluminum wire, can be ball bonded on the contact point **8000** exposed by the opening **990** in the polymer layer **99** and wedge bonded on a contact point **15** of the printed circuit board **13**. Next, a polymer material, such as epoxy-based material, can be molded over the printed circuit board (PCB) **13**, enclosing the wire **89'** and the DRAM chip **10'**. Next, the printed circuit board (PCB) **13** can be singularized into multiple portions using a mechanical cutting pro-

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cess. Next, multiple solder balls **19** containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy can be ball mounted onto a bottom surface of the singularized printed circuit board (PCB) **13**.

[0548] Alternatively, multiple DRAM chips **10'** can be stacked over the printed circuit board (PCB) **13**, as shown in FIG. **23**M. A bottom one of the DRAM chips **10'** can be first mounted to the printed circuit board (PCB) **13**, ball-grid-array (BGA) substrate, via an adhesive material **11**, such as silver epoxy. Next, a wire **89'**, such as gold wire, copper wire or aluminum wire, can be ball bonded on the contact point **8000** of the bottom one of the DRAM chips **10'**, exposed by the opening **990** in the polymer layer **99** and wedge bonded on a contact point **15** of the printed circuit board **13**. Next, a dump bump, such as silicon or copper, can be adhered to a top surface of the bottom one of the DRAM chips **10'** via an adhesive material **11**, such as silver epoxy. Next, a top one of the DRAM chips **10'** can be mounted to the dummy bump **19**, via an adhesive material **11**, such as silver epoxy. Next, a wire **89'**, such as gold wire, copper wire or aluminum wire, can be ball bonded on the contact point **8000** of the top one of the DRAM chips **10'**, exposed by the opening **990** in the polymer layer **99** and wedge bonded on the contact point **15** of the printed circuit board **13**. The only one contact pad **15** of the printed circuit board (PCB) **13** can be connected to the two contact points **8000** of the top and bottom chips **10'** through the two wirebonded wires **89'**.

[0549] Referring to FIG. **23**N showing a top view of a chip package for the DRAM chip **10'** and to FIGS. **23**A-**23**M, original pads **600** exposed by openings in a passivation layer **5** are aligned in a center line of the DRAM chip **10'**, and relocated pads **8000** connected to the original pads **600** through the patterned circuit layer **801** over the passivation layer **5** are arranged close to the edges of the DRAM chip **10'**, leading the relocated pads **8000** to be readily wirebonded by the wires **89'**.

[0550] After one or more DRAM chips **10'** are packaged as shown in FIGS. **21**L and **21**M, an electrical testing process can be performed to initially verify good packages, non-repairable bad packages and repairable bad packages. The initially verified repairable bad packages can be repaired by the previously described E-fuse repairing process. Next, another electrical testing process can be performed to check if the repaired packages are good. Next, the initially verified good packages and the repaired good packages can be burned in. Next, another electrical testing process can be performed to check if the burned-in packages continue good.

[0551] Alternatively, other chips, such as flash memory chips, SRAM chips or logic chips, can be packaged as the process for packaging the DRAM chips **10'** as shown in FIGS. **23**A-**23**M is performed.

[0552] The above description focus on a top post-passivation technology, that is, the over-passivation scheme **102** can be formed over the passivation layer **5** at the active side of the silicon substrate **1**. FIGS. **1**B-**1**D, **3**B-**3**D, **5**B, **5**K, **5**S, **5**U, **5**V-**5**Z, **7**B-**7**D, **8**A-**8**F, **10**A-**10**I, **12**B-**12**D, **14**B-**14**D, **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H, **20** and **23**K show that various types of the over-passivation schemes **102** formed over the passivation layer **5** at the active side of the silicon substrate **1**. The below description focus on a bottom structure technology, that is, a bottom scheme **103** can be formed at the backside **1***a* of the thinned silicon substrate **1**. The elements having same reference numbers in this specification can be reference to one another.

[0553] FIG. **24**A shows the silicon substrate **1** and other elements as described above in the semiconductor wafer **10**, and the silicon substrate **1** has a thickness t**1** between 600 and 1000 micrometers, between 50 micrometers and 1 millimeter or between 75 and 250 micrometers. Alternatively, the silicon substrate **1** can be replaced with other semiconductor substrate, such as silicon-germanium (SiGe) substrate or gallium arsenide (GaAs) substrate.

[0554] Referring to FIG. **24**B, the semiconductor wafer **10** is flipped over, and then the silicon substrate **1** is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) a backside **1***a* of the silicon substrate **1**. Alternatively, the previously described step of flipping over the semiconductor wafer **10** can be performed after the previously described step of thinning the silicon substrate **1**, to perform the following processes.

[0555] Next, referring to FIG. **24**C, multiple through-silicon vias (TSV) **11***a*, **11***b*, **11***c*, **11***d* and **11***e* are formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing regions **60***a* of the fine-line metal layers **60** and **632***c*, and an insulating layer **3** is formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*. The through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. The through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* may have a diameter or width W**1** between 5 and 100 micrometers or between 3 and 50 micrometers, and a depth between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers. The insulating layer **3**, for example, may include a nitride layer, such as silicon-nitride layer, a polymer layer, such as polyimide layer, benzocyclobutene layer or polybenzoxazole layer, a silicon-oxynitride layer, a silicon-carbon-nitride (SiCN) layer, a silicon-oxycarbide (SiOC) layer or a silicon-oxide layer.

[0556] FIGS. **24**D-**24**H are cross-sectional views showing a process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and the insulating layer **3** according to the present disclosure. Referring to FIG. **24**D, after the step illustrated in FIG. **24**B, a photoresist layer **28** is spin-on coated or laminated on the backside **1***a* of the thinned silicon substrate **1**, and multiple ring-shaped openings **28***a* are formed in the photoresist layer **28**, exposing the backside **1***a* of the thinned silicon substrate **1**, using an exposure process and developing process. FIG. **24**E is a schematic top view showing the ring-shaped openings **28***a* in the photoresist layer **28**. Next, referring to FIG. **24**F, multiple through-silicon ring-shaped openings **11***g* each having a transverse width W**2** between 1 and 20 micrometer are formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, penetrating completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**, by dry etching the thinned silicon substrate **1** and the dielectric layer(s) **30** under the ring-shaped openings **28***a* in the photoresist layer **28**, for example, using anisotropic reactive ion etching. Next, the photoresist layer **28** is removed, as shown in FIG. **24**G. Next, referring to FIG. **24**H, the insulating layer **3**, such as polymer layer, polyimide layer, benzocyclobutene (BCB) layer, polybenzoxazole (PBO) layer, silicon-nitride layer, silicon-oxide layer, silicon-oxynitride layer, silicon-oxycarbide (SiOC) layer or silicon-carbon-nitride (SiCN) layer, having a thickness t**3** between 0.5 and 20 micrometers or between 0.01 and 5 micrometers is

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formed in the through-silicon ring-shaped openings **11***g* and on the backside **1***a* of the thinned silicon substrate **1**. Next, multiple portions of the thinned silicon substrate **1** surrounded by the insulating layer **3** in the through-silicon ring-shaped openings **11***g* are removed using a dry etching process, such as fluorine and carbon based anisotropic reactive ion etching, and accordingly the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* are formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60** and **632***c*, as shown in FIG. **24**C, and the insulating layer **3** is formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*.

[0557] FIGS. **24**I-**24**N are cross-sectional views showing another process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and the insulating layer **3** according to the present disclosure. Referring to FIG. **24**I, an etching stop layer **3***a*, such as silicon-nitride layer, silicon-oxide layer or polymer layer, having a thickness t**4** between 0.3 and 40 micrometers is formed on the backside **1***a* of the thinned silicon substrate **1**. For example, the etching stop layer **3***a* can be formed by a suitable process or processes, e.g., by depositing a silicon-nitride or silicon-carbon-nitride layer having a thickness between 0.2 and 1.2 micrometers on the backside **1***a* of the thinned silicon substrate **1** using a chemical mechanical deposition (CVD) process. Alternatively, the etching stop layer **3***a* can be formed by a suitable process or processes, e.g., by depositing a silicon-oxide or silicon-oxycarbide layer having a thickness between 0.2 and 1.2 micrometers on the backside **1***a* of the thinned silicon substrate **1** using a chemical mechanical deposition (CVD) process, and then depositing a silicon-nitride or silicon-carbon-nitride layer having a thickness between 0.2 and 1.2 micrometers on the silicon-oxide or silicon-oxycarbide layer using a chemical mechanical deposition (CVD) process. Alternatively, the etching stop layer **3***a* can be formed by a suitable process or processes, e.g., by depositing a silicon-nitride layer having a thickness between 0.2 and 1.2 micrometers on the bottom backside **1***a* of the thinned silicon substrate **1** using a chemical mechanical deposition (CVD) process, and then coating a polymer layer having a thickness between 2 and 30 micrometers on the silicon-nitride or silicon-carbon-nitride layer.

[0558] Referring to FIG. **24**J, after the step illustrated in FIG. **24**I, a photoresist layer **54** is spin-on coated or laminated on the etching stop layer **3***a*, and multiple openings **54***a* are formed in the photoresist layer **54** and expose the etching stop layer **3***a* using an exposure process and developing process. Next, referring to FIG. **24**K, the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* are formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, penetrating completely through the etching stop layer **3***a*, the thinned silicon substrate **1** and the dielectric layer(s) **30** and exposing the regions **60***a* of the fine-line metal layers **60** and **632***c*, by dry etching the etching stop layer **3***a*, the thinned silicon substrate **1** and the dielectric layer(s) **30** under the openings **54***a* in the photoresist layer **54**, for example, using fluorine and carbon based anisotropic reactive ion etching. Next, the photoresist layer **28** is removed, as shown in FIG. **24**L. Next, referring to FIG. **24**M, an insulating layer **3***b*, such as polymer layer, polyimide layer, benzocyclobutene (BCB) layer, polybenzoxazole (PBO) layer, silicon-nitride layer, silicon-oxide layer, silicon-oxynitride layer, silicon-oxycarbide (SiOC) layer or silicon-carbon-nitride (SiCN) layer, having a thickness t**5** between 0.1 and 10 micrometers is formed on the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the etching stop layer **3***a* and on the regions **60***a* of the fine-line metal layers **60** and **632***c* exposed by the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*. Next, referring to FIG. **24**N, the insulating layer **3***b* formed on the etching stop layer **3***a* and on the regions **60***a* of the fine-line metal layers **60** and **632***c* are removed using a dry etching process, such as anisotropic reactive ion etching. Accordingly, the regions **60***a* of the fine-line metal layers **60** and **632***c* are exposed through the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and the etching stop layer **3***a* has a top surface uncovered by the insulating layer **3***b*. The etching stop layer **3***a* and the insulating layer **3***b* composes the insulating layer **3**.

[0559] For easy description, the insulating layer **3** shown in the following process can be referenced by the insulating layer **3** made as illustrated in FIGS. **24**D-**24**H or the insulating layer **3**, composed of the etching stop layer **3***a* and the insulating layer **3***b*, made as illustrated in FIGS. **24**I-**24**N.

[0560] FIGS. **25**A-**25**L are cross-sectional views showing a process for forming a bottom scheme **103** of a bottom structure technology at a backside of a semiconductor wafer according to the present disclosure. Referring to FIG. **25**A, after forming the insulating layer **3** and the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, a metal layer **4** can be formed on the insulating layer **3**, on the regions **60***a* of the fine-line metal layers **60** and **632***c* exposed by the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*. The metal layer **4** can be formed by a suitable process or processes, e.g., by depositing an adhesion/barrier layer **4***a* on the insulating layer **3**, in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, and on the regions **60***a* of the fine-line metal layers **60** and **632***c* exposed by the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, and then depositing a seed layer **4***b* on the adhesion/barrier layer **4***a*.

[0561] The adhesion/barrier layer **4***a* at the bottom of the metal layer **4** may be formed by a suitable process or processes, e.g., by sputtering or chemical vapor depositing (CVD) a titanium-containing layer, such as titanium-nitride layer, titanium layer or titanium-tungsten-alloy layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the insulating layer **3**, at the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, and on an aluminum layer, an electroplated copper layer, a tantalum-nitride layer, a titanium-nitride layer, a tantalum layer or a titanium layer of the fine-line metal layers **60** and **632***c* exposed by the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*. Alternatively, the adhesion/barrier layer **4***a* at the bottom of the metal layer **4** may be formed by a suitable process or processes, e.g., by sputtering or chemical vapor depositing a chromium-containing layer, such as chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the insulating layer **3**, at the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, and on an aluminum layer, an electroplated copper layer, a tantalum-nitride layer, a titanium-nitride layer, a tantalum layer or a titanium layer of the fine-line metal layers **60** and **632***c* exposed by the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*. Alternatively, the adhesion/barrier layer **4***a* at the bottom of the metal layer **4** may be formed by a suitable process or

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processes, e.g., by sputtering or chemical vapor depositing a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the insulating layer **3**, at the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, and on an aluminum layer, an electroplated copper layer, a tantalum-nitride layer, a titanium-nitride layer, a tantalum layer or a titanium layer of the fine-line metal layers **60** and **632***c* exposed by the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*.

[0562] The seed layer **4***b* at the top of the metal layer **4** may be formed by a suitable process or processes, e.g., by sputtering or chemical vapor depositing a copper layer, an aluminum layer, a nickel layer or a silver layer with a thickness smaller than 1 micrometer, such as between 0.005 and 1 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **4***a* of any previously described material. Alternatively, the seed layer **4***b* at the top of the metal layer **4** may be formed by a suitable process or processes, e.g., by sputtering or chemical vapor depositing a gold layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the adhesion/barrier layer **4***a* of any previously described material.

[0563] Referring to FIG. **25**B, after forming the metal layer **4**, a photoresist layer **29**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1.5 micrometers, such as between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, is formed on the seed layer **4***b* of the metal layer **4** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **29** is patterned with the processes of exposure and development to form multiple openings **29***a* in the photoresist layer **29** exposing the seed layer **4***b* of the metal layer **4**, as shown in FIG. **25**C. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **29** during the process of exposure.

[0564] For example, the photoresist layer **29** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer having a thickness between 5 and 30 micrometers, and preferably between 10 and 25 micrometers, on the seed layer **4***a* of the metal layer **4**, then exposing the photosensitive polymer layer using a 1× stepper or a contact aligner with at least two of G-line, H-line and I-line, and G-line has a wavelength ranging from, e.g., about 434 to 438 nm, H-line has a wavelength ranging from, e.g., about 403 to 407 nm, and I-line has a wavelength ranging from, e.g., about 363 to 367 nm, then developing the exposed polymer layer by spraying and puddling a developer on the photoresist layer **29** or by immersing the photoresist layer **29** into a developer, and then cleaning the semiconductor wafer using deionized wafer and drying the semiconductor wafer by spinning the semiconductor wafer. After development, a scum removal process of removing the residual polymeric material or other contaminants from the seed layer **4***b* of the metal layer **4** may be conducted by using an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By these processes, the photoresist layer **29** can be patterned with the openings **29***a* exposing the seed layer **4***b* of the metal layer **4**.

[0565] Next, referring to FIG. **25**D, a bulk metal layer **9** is formed in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* by a process including an electroplating process. The bulk metal layer **9** may have a thickness larger than 1 micrometer, such as between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, and larger than that of the seed layer **4***b*, that of the adhesion/barrier layer **4***a* and that of each of the fine-line metal layers **60**, respectively. The bulk metal layer **9** may include copper, gold, nickel, aluminum, silver, platinum, solder or a composite of the previously described materials.

[0566] For example, the bulk metal layer **9** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably the previously described copper layer **4***b*, exposed by the openings **29***a* with an electroplating solution containing $CuSO_4$, $Cu(CN)_2$ or $CuHPO_4$.

[0567] Alternatively, the bulk metal layer **9** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating an aluminum layer, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably formed by a suitable process or processes, e.g., by the previously described aluminum layer or copper layer **4***b*, exposed by the openings **29***a*.

[0568] Alternatively, the bulk metal layer **9** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness between 0.5 and 30 micrometers, between 1 and 10 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably the previously described gold layer **4***b*, exposed by the openings **29***a* with an electroplating solution containing gold of between 1 and 20 grams per litter (g/l), and preferably between 5 and 15 g/l, and sulfite ion of 10 and 120 g/l, and preferably between 30 and 90 g/l. The electroplating solution may further include sodium ion, to be turned into a solution of gold sodium sulfite ($Na_3Au(SO_3)_2$), or may further include ammonium ion, to be turned into a solution of gold ammonium sulfite ($(NH_4)_3[Au(SO_3)_2]$). The operational parameters of electroplating the gold layer are described below:

[0569] 1. The previously described electroplating solution can be at a temperature of between 30 and 70° C., and preferably between 45 and 65° C., to electroplate the gold layer on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a*.

[0570] 2. The previously described electroplating solution can be used to electroplate the gold layer on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* through an electric current with a current density at between 1 and 10 mA/cm^2, and preferably between 4 and 6 mA/cm^2.

[0571] 3. The previously described electroplating solution may have a pH value of between 6 and 9, and preferably of between 7 and 8.5, to electroplate the gold layer on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a*.

[0572] Alternatively, the bulk metal layer **9** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably the previously described

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copper layer **4***b*, exposed by the openings **29***a* using the previously described electroplating solution for electroplating copper, and then electroplating a nickel layer, a top metal layer of the bulk metal layer **9**, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **29***a* and on the electroplated copper layer in the openings **29***a* using an electroplating solution containing $NiSO_4$ or Ni sulfamate or $Ni(NH_2SO_3)_2$ or electroless plating a nickel layer, a top metal layer of the bulk metal layer **9**, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **29***a* and on the electroplated copper layer in the openings **29***a* using an electroless plating solution containing Ni and $NaPO_2H_2$ (Sodium Hypophosphite).

[0573] Alternatively, the bulk metal layer **9** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably formed by a suitable process or processes, e.g., by the previously described copper layer or nickel layer **4***b*, exposed by the openings **29***a* using the previously described electroplating solution for electroplating nickel.

[0574] Alternatively, the bulk metal layer **9** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer **126**, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably the previously described copper layer **4***b*, exposed by the openings **29***a* using the previously described electroplating solution for electroplating copper, next electroplating or electroless plating a nickel layer **127**, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **29***a* and on the electroplated copper layer in the openings **29***a* using the previously described electroplating solution for electroplating or electroless plating nickel, and then electroplating a gold layer **128**, a top metal layer of the bulk metal layer **9**, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **29***a* and on the electroplated or electroless plated nickel layer in the openings **29***a* using the previously described electroplating solution for electroplating gold, or electroless plating a gold layer **128**, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **29***a* and on the electroplated or electroless plated nickel layer in the openings **29***a* using an electroless plating solution containing gold salt, such as $AuNaSO_3$ or AuCN and a reduction agent, such as benzoic or phenyl.

[0575] Alternatively, the bulk metal layer **9** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer **126**, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably the previously described copper layer **4***b*, exposed by the openings **29***a* using the previously described electroplating solution for electroplating copper, next electroplating or electroless plating a nickel layer **127**, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **29***a* and on the electroplated copper layer in the openings **29***a* using the previously described electroplating solution for electroplating or electroless plating nickel, and then electroplating a palladium layer **128**, a top metal layer of the bulk metal layer **9**, to a thickness between 0.005 and 5 micrometers, and preferably between 0.05 and 1 micrometers, in the openings **29***a* and on the electroplated or electroless plated nickel layer in the openings **29***a* using an electroplating solution containing palladium and ammonia, or electroless plating a palladium layer **128**, a top metal layer of the bulk metal layer **9**, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **29***a* and on the electroplated or electroless plated nickel layer in the openings **29***a* using an electroless plating solution containing palladium, ammonia and a reduction agent, such as hydrozine.

[0576] Alternatively, the bulk metal layer **9** can be composed of four metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, between 2 and 20 micrometers or between 5 and 150 micrometers, in the openings **29***a* and on the seed layer **4***b*, preferably the previously described copper layer **4***b*, exposed by the openings **29***a* using the previously described electroplating solution for electroplating copper, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **29***a* and on the electroplated copper layer in the openings **29***a* using the previously described electroplating solution for electroplating or electroless plating nickel, next electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 5 micrometers, and preferably between 0.05 and 1 micrometers, in the openings **29***a* and on the electroplated or electroless plated nickel layer in the openings **29***a* using the previously described electroplating solution for electroplating or electroless plating palladium, and then electroplating or electroless plating a gold layer, a top metal layer of the bulk metal layer **9**, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **29***a* and on the electroplated or electroless plated palladium layer in the openings **29***a* using the previously described electroplating solution for electroplating or electroless plating gold.

[0577] Referring to FIG. **25**E, after forming the bulk metal layer **9**, the photoresist layer **29** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **29** could remain on the metal layer **4** not under the bulk metal layer **9**. Thereafter, the residuals can be removed from the metal layer **4** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0578] Next, referring to FIG. **25**F, the metal layer **4** not under the bulk metal layer **9** is removed by etching the seed layer **4***b* not under the bulk metal layer **9**, and then etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**.

[0579] In a case, the seed layer **4***b* and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** can be subsequently removed by a dry etching method. As to the dry etching method, both the seed layer **4***b* and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** can be subsequently removed by an Ar sputtering etching process; alternatively, both the seed layer **4***b* and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** can be subsequently removed by a reactive ion etching (RIE) process; alternatively, the seed layer **4***b* not under the bulk metal layer **9** can be removed by an Ar sputtering etching process, and the adhesion/barrier

layer **4***a* not under the bulk metal layer **9** can be removed by a reactive ion etching (RIE) process.

[0580] In another case, the seed layer **4***b* and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** can be subsequently removed by a wet etching method. As to the wet etching method, when the seed layer **4***b* is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4; when the seed layer **4***b* is a gold layer, it can be etched with an iodine-containing solution, such as a solution containing potassium iodide; when the adhesion/barrier layer **4***a* is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide; when the adhesion/barrier layer **4***a* is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide; when the adhesion/barrier layer **4***a* is a chromium layer, it can be etched with a solution containing potassium ferricyanide.

[0581] In another case, the seed layer **4***b*, such as copper, not under the bulk metal layer **9** can be removed by a solution containing NH_4OH or a solution containing H_2SO_4, and the adhesion/barrier layer **210** not under the bulk metal layer **9** can be removed by a reactive ion etching (RIE) process or an Ar sputtering etching process.

[0582] In another case, the seed layer **4***b*, such as gold, not under the bulk metal layer **9** can be etched with an iodine-containing solution, such as a solution containing potassium iodide, and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** can be removed by a reactive ion etching (RIE) process or an Ar sputtering etching process.

[0583] After etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**, multiple interconnecting structures **88** provided by the metal layers **4** and **9** can be formed in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and sidewalls of the bulk metal layer **9** are not covered by the metal layer **4**.

[0584] Referring to FIG. **25**G, after the step illustrated in FIG. **25**F, a polymer layer **14** can be formed on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and on the insulating layer **3** using a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and an opening **14***a* in the polymer layer **14** is over a region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and exposes it. The polymer layer **14** has a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0585] In a case, the polymer layer **14** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer having a thickness between 6 and 50 micrometers on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form an opening exposing the bulk metal layer **9**, then curing or heating the developed polyimide layer at a temperature between 180 and 400° C., between 180 and 250° C., between 250 and 290° C., between 290 and 400° C. or between 200 and 390° C. for a time between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness between 3 and 25 micrometers, and then removing the residual polymeric material or other contaminants from the exposed bulk metal layer **9** with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By the way, the polymer layer **14** can be formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, and the opening **14***a* formed in the polymer layer **14** exposes the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**.

[0586] In another case, the polymer layer **14** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polybenzoxazole layer having a thickness between 3 and 25 micrometers on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, then baking the spin-on coated polybenzoxazole layer, then exposing the baked polybenzoxazole layer using a 1× stepper or a 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polybenzoxazole layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polybenzoxazole layer, then developing the exposed polybenzoxazole layer to form an opening exposing the bulk metal layer **9**, then curing or heating the developed polybenzoxazole layer at a temperature between 150 and 250° C., and preferably between 180 and 250° C., or between 200 and 400° C., and preferably between 250 and 350° C., for a time between 5 and 180 minutes, and preferably between 30 and 120 minutes, in a nitrogen ambient or in an oxygen-free ambient, the cured polybenzoxazole layer having a thickness between 3 and 25 μm, and then removing the residual polymeric material or other contaminants from the exposed bulk metal layer **9** with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By the way, the polymer layer **14** can be formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, and the opening **14***a* formed in the polymer layer **14** exposes the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**.

[0587] Next, referring to FIG. **25**H, an adhesion/barrier layer **16** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **14** and on the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the opening **14***a* by using a physical vapor deposition (PVD) process, such as

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sputtering process or evaporation process, and then a seed layer **18** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **16** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **16** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **18** may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0588] For example, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **14** and on the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the opening **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the titanium-containing layer.

[0589] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the polymer layer **14** and on the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the opening **14***a* and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the titanium-tungsten-alloy layer.

[0590] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **14** and on the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the opening **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the tantalum-containing layer.

[0591] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **14** and on the region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the opening **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the chromium-containing layer.

[0592] Referring to FIG. **25**I, after forming the seed layer **18**, a photoresist layer **31**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 5 micrometers, such as between 10 and 150 micrometers, and preferably between 15 and 50 micrometers, is formed on the seed layer **18** of any previously described material by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **31** is patterned with the processes of exposure and development to form an opening **31***a* in the photoresist layer **31** exposing the seed layer **18** of any previously described material. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **31** during the process of exposure.

[0593] For example, the photoresist layer **31** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer having a thickness larger than 5 micrometers, such as between 10 and 150 micrometers, and preferably between 15 and 50 micrometers, on the seed layer **18** of any previously described material, then exposing the photosensitive polymer layer using a 1× stepper or a contact aligner with at least two of G-line, H-line and I-line, and G-line has a wavelength ranging from, e.g., about 434 to 438 nm, H-line has a wavelength ranging from, e.g., about 403 to 407 nm, and I-line has a wavelength ranging from, e.g., about 363 to 367 nm, then developing the exposed polymer layer by spraying and puddling a developer on the photoresist layer **31** or by immersing the photoresist layer **31** into a developer, and then cleaning the semiconductor wafer using deionized wafer and drying the semiconductor wafer by spinning the semiconductor wafer. After development, a scum removal process of removing the residual polymeric material or other contaminants from the seed layer **18** may be conducted by using an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By these processes, the photoresist layer **31** can be patterned with the opening **31***a* exposing the seed layer **18**.

[0594] Referring to FIG. **25**J, after the step illustrated in FIG. **25**I, a metal bump or pillar **27** can be formed on the seed layer **18** of any previously described material exposed by the opening **31***a* and in the opening **31***a*. The metal bump or pillar **27** may have a thickness larger than 5 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, and larger than that of the seed layer **18**, that of the adhesion/barrier layer **16** and that of each of the fine-line metal layers **60**, respectively. The metal bump or pillar **27** may have a width larger than 1 micrometer, such as between 5 and 150 micrometers, and preferably between 5 and 50 micrometers, and larger than that of each of the fine-line metal layers **60**. The material of the metal bump or pillar **27** may include copper, gold, nickel, aluminum, silver, solder, platinum or a composite of the previously described materials. The metal bump or pillar **27** can be used to be bonded with

an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate.

[0595] For example, the metal bump or pillar **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**.

[0596] Alternatively, the metal bump or pillar **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness between 5 and 30 micrometers, and preferably between 10 and 25 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described gold layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating gold of the bulk metal layer **9**.

[0597] Alternatively, the metal bump or pillar **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer or nickel layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating nickel of the bulk metal layer **9**.

[0598] Alternatively, the metal bump or pillar **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, in the opening **31***a* and on the electroplated copper layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0599] Alternatively, the metal bump or pillar **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the opening **31***a* and on the electroplated copper layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel Of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the opening **31***a* and on the electroplated or electroless plated nickel layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0600] Alternatively, the metal bump or pillar **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the opening **31***a* and on the electroplated copper layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the opening **31***a* and on the electroplated or electroless plated nickel layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0601] Alternatively, the metal bump or pillar **27** can be composed of four metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the opening **31***a* and on the electroplated copper layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, next electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the opening **31***a* and on the electroplated or electroless plated nickel layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the opening **31***a* and on the electroplated or electroless plated palladium layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0602] Alternatively, the metal bump or pillar **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an

indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometer, in the opening **31***a* and on the electroplated copper layer in the opening **31***a*.

[0603] Alternatively, the metal bump or pillar **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 60 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer or nickel layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometer, in the opening **31***a* and on the electroplated nickel layer in the opening **31***a*.

[0604] Alternatively, the metal bump or pillar **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the opening **31***a* and on the electroplated copper layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, in the opening **31***a* and on the electroplated or electroless plated nickel layer in the opening **31***a*.

[0605] Alternatively, the metal bump or pillar **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 10 micrometers, and preferably between 3 and 8 micrometers, in the opening **31***a* and on the seed layer **18**, preferably the previously described copper layer **18**, exposed by the opening **31***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the opening **31***a* and on the electroplated copper layer in the opening **31***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 30 and 250 micrometers, and preferably between 50 and 150 micrometers, in the opening **31***a* and on the electroplated or electroless plated nickel layer in the opening **31***a*.

[0606] Next, referring to FIG. **25**K, the photoresist layer **31** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **31** could remain on the seed layer **18** not under the metal bump or pillar **27**. Thereafter, the residuals can be removed from the seed layer **18** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. Next, referring to FIG. **25**L, the seed layer **18** not under the metal bump or pillar **27** is removed, and then the adhesion/barrier layer **16** not under the metal bump or pillar **27** is removed.

[0607] In a case, the seed layer **18** and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be subsequently removed by a dry etching method. As to the dry etching method, both the seed layer **18** and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be subsequently removed by an Ar sputtering etching process; alternatively, both the seed layer **18** and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be subsequently removed by a reactive ion etching (RIE) process; alternatively, the seed layer **18** not under the metal bump or pillar **27** can be removed by an Ar sputtering etching process, and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be removed by a reactive ion etching (RIE) process.

[0608] In another case, the seed layer **18** and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be subsequently removed by a wet etching method. As to the wet etching method, when the seed layer **18** is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4; when the seed layer **18** is a gold layer, it can be etched with an iodine-containing solution, such as a solution containing potassium iodide; when the adhesion/barrier layer **16** is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide; when the adhesion/barrier layer **16** is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide; when the adhesion/barrier layer **16** is a chromium layer, it can be etched with a solution containing potassium ferricyanide.

[0609] In another case, the seed layer **18**, such as copper, not under the metal bump or pillar **27** can be removed by a solution containing NH_4OH or a solution containing H_2SO_4, and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be removed by a reactive ion etching (RIE) process or an Ar sputtering etching process.

[0610] In another case, the seed layer **18**, such as gold, not under the metal bump or pillar **27** can be etched with an iodine-containing solution, such as a solution containing potassium iodide, and the adhesion/barrier layer **16** not under the metal bump or pillar **27** can be removed by a reactive ion etching (RIE) process or an Ar sputtering etching process.

[0611] In case the adhesion/barrier layer **16** not under the metal bump or pillar **27** is removed using a wet etching process, an undercut is formed under the metal bump or pillar **27** overhanging the adhesion/barrier layer **16**. The adhesion/barrier layer **16** under the metal bump or pillar **27** has a first sidewall recessed from a second sidewall of the metal bump or pillar **27**, and a distance d**1** between the first sidewall and the second sidewall is between 0.3 and 2 micrometers.

[0612] Accordingly, as shown in FIG. **25**L, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the interconnecting

structures **88** provided by the metal layers **4** and **9**, the polymer layer **14**, the metal layers **16** and **18**, and the metal bump or pillar **27**, and the opening **14***a* in the polymer layer **14** is over the interconnecting structure **88**. After the step illustrated in FIG. **25**L, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0613] Alternatively, after the step illustrated in FIG. **25**L, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0614] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**L. After the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**L, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0615] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bump or pillar **27** of the bottom scheme **103**. The semiconductor chip includes the bottom scheme **103**, and the bottom scheme **103** includes the insulating layer **3** on the backside **1***a* of the thinned silicon substrate **1** and in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, the interconnecting structures **88** at the backside **1***a* of the thinned silicon substrate **1**, in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and on the insulating layer **3**, the polymer layer **14** at the backside **1***a* of the thinned silicon substrate **1**, on the interconnecting structures **88** and on the insulating layer **3**, the metal bump or pillar **27** at the backside **1***a* of the thinned silicon substrate **1**, on the interconnecting structure **88** and on the polymer layer **14**, the adhesion/barrier layer **16** between the bulk metal layer **9** and the metal bump or pillar **27**, and the seed layer **18** between the adhesion/barrier layer **16** and the metal bump or pillar **27**. The interconnecting structures **88** connects the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, connects the off-chip buffer **42** to the metal bump or pillar **27**, and connects the internal circuits **21**, **22**, **23** and **24** to the metal bumps or pillars **27**. The off-chip ESD (electro static discharge) circuit **43** is connected to the off-chip buffer **42** through the fine-line metal trace **639**, and to the interconnecting structure **88** through the fine-line metal trace **639**.

[0616] FIG. **25**M is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a flux **32** can be formed in the openings **531**, **532**, **534**, **539** and **539'** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the interconnecting structures **88**, the polymer layer **14** and the metal bump or pillar **27** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**L. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**L can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0617] After forming the structure shown in FIG. **25**M, the flux **32** is removed. Next, with the following steps being illustrated with reverse figures for simple explanation, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bump or pillar **27** of the bottom scheme **103**, and/or to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20**.

[0618] FIG. **25**N is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, multiple metal pads, bumps or traces **34***a* composed of two metal layers **32** and **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The metal layer **32** is formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539**, and the metal layer **34** is formed on the metal layer **32**, and the metal layer **34** is not covered by the metal layer **32**.

[0619] The metal pad, bump or trace **34***a* has a thickness larger than 1 micrometer, such as between 1 and 20 micrometers or between 5 and 60 micrometers, and a width larger than that of the metal trace or pad **600** and larger than 3 micrometers, such as between 5 and 60 micrometers, and the metal trace or pad **600** may have a width smaller than 1 micrometer,

such as between 0.05 and 0.95 micrometers. The metal pads, bumps or traces **34***a* can be used to be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by bonding the metal pads, bumps or traces **34***a* to the first external circuit or by wirebonding gold wires or copper wires to the metal pads, bumps or traces **34***a* and to the first external circuit.

[0620] For example, the metal pads, bumps or traces **34***a* can be formed by a suitable process or processes, e.g., by a process including sputtering an adhesion/barrier layer **32**, such as titanium layer, titanium-tungsten-alloy layer, titanium-nitride layer, tantalum layer or tantalum-nitride layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, next sputtering an aluminum-containing layer **34**, such as aluminum layer or aluminum-copper-alloy layer, having a thickness between 0.5 and 10 micrometers, and preferably between 1 and 5 micrometers, on the adhesion/barrier layer **32**, next forming a patterned photoresist layer on the aluminum-containing layer **34**, next etching the aluminum-containing layer **34** not under the patterned photoresist layer, next etching the adhesion/barrier layer **32** not under the patterned photoresist layer, and then removing the patterned photoresist layer. Accordingly, the metal pads, bumps or traces **34***a* provided by the adhesion/barrier layer **32** and the aluminum-containing layer **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The aluminum-containing layer **34** of the metal pad, bump or trace **34***a* can be used to be connected to the first external circuit by wirebonding a gold wire or a copper wire to the aluminum-containing layer **34** and to the first external circuit or by bonding aluminum-containing layer **34** with a gold layer or a tin-alloy layer of the first external circuit.

[0621] Alternatively, the metal pads, bumps or traces **34***a* can be formed by a suitable process or processes, e.g., by a process including sputtering an adhesion/barrier layer **32**, such as titanium layer, titanium-tungsten-alloy layer, titanium-nitride layer, tantalum layer or tantalum-nitride layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, next sputtering a seed layer of gold (not shown) having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **32**, next forming a patterned photoresist layer on the seed layer of gold, and multiple openings in the patterned photoresist layer expose multiple regions of the seed layer of gold, next electroplating a gold layer **34** having a thickness larger than 1 micrometer, such as between 1 and 25 micrometers, and preferably between 2 and 10 micrometers, on the regions of the seed layer of gold exposed by the openings in the patterned photoresist layer, next removing the photoresist layer, next etching the seed layer of gold not under the gold layer **34**, and then etching the adhesion/barrier layer **32** not under the gold layer **34**. Accordingly, the metal pads, bumps or traces **34***a* provided by the adhesion/barrier layer **32**, the seed layer of gold and the gold layer **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The gold layer **34** of the metal pad, bump or trace **34***a* can be used to be connected to the first external circuit by wirebonding a gold wire or a copper wire to the gold layer **34** and to the first external circuit or by bonding the gold layer **34** with a gold layer or a tin-alloy layer of the first external circuit.

[0622] Alternatively, the metal pads, bumps or traces **34***a* can be formed by a suitable process or processes, e.g., by a process including electroless plating a nickel layer **32** with a thickness between 1 and 10 micrometers, and preferably between 2 and 8 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, and then electroless plating the metal layer **34**, such as gold layer or palladium layer, with a thickness between 200 angstroms and 2 micrometers, and preferably between 500 angstroms and 5,000 angstroms, on the nickel layer **32**. Accordingly, the metal pads, bumps or traces **34***a* provided by the nickel layer **32** and the metal layer **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The metal layer **34** of the metal pad, bump or trace **34***a* can be used to be connected to the first external circuit by wirebonding a gold wire or a copper wire to the metal layer **34** and to the first external circuit or by bonding the metal layer **34** with a gold layer or a tin-alloy layer of the first external circuit.

[0623] Alternatively, the metal pads, bumps or traces **34***a* can be formed by a suitable process or processes, e.g., by a process including sputtering an adhesion/barrier layer **32**, such as titanium layer, titanium-tungsten-alloy layer, titanium-nitride layer, chromium layer, tantalum layer or tantalum-nitride layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, next sputtering a seed layer of copper (not shown) having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **32**, next forming a patterned photoresist layer on the seed layer of copper, and multiple openings in the patterned photoresist layer expose multiple regions of the seed layer of copper, next electroplating a copper layer **34** having a thickness larger than 1 micrometer, such as between 1 and 100 micrometers, and preferably between 5 and 60 micrometers, on the regions of the seed layer of copper exposed by the openings in the patterned photoresist layer, next removing the photoresist layer, next etching the seed layer of copper not under the copper layer **34**, and then etching the adhesion/barrier layer **32** not under the copper layer **34**. Accordingly, the metal pads, bumps or traces **34***a* provided by the adhesion/barrier layer **32**, the seed layer of copper and the copper layer **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The copper layer **34** of the metal pad, bump or trace **34***a* can be used to be connected to the first external circuit by wirebonding a gold wire or a copper wire to the copper layer **34** and to the first external circuit or by bonding the copper layer **34** with a gold layer or a tin-alloy layer of the first external circuit.

[0624] Alternatively, the metal pads, bumps or traces **34***a* can be formed by a suitable process or processes, e.g., by a process including sputtering an adhesion/barrier layer **32**, such as titanium layer, titanium-tungsten-alloy layer, titanium-nitride layer, chromium layer, tantalum layer or tantalum-nitride layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, next sputtering a seed layer of copper (not shown) having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **32**, next forming a patterned photoresist layer on the seed layer of copper, and multiple openings in the patterned photoresist layer expose multiple regions of the seed layer of copper, next electroplating a copper layer **34** having a thickness larger than 1 micrometer, such as between 1 and 100 micrometers, and preferably between 5 and 60 micrometers, on the regions of the seed layer of copper exposed by the openings in the patterned photoresist layer, next electroplating or electroless plating a nickel layer (not shown) having a thickness between 0.5 and 8 micrometers, and preferably between 1 and 5 micrometers, on the copper layer **34** in the openings in the patterned photoresist layer, next electroplating or electroless plating a gold layer (not shown) having a thickness between 0.1 and 10 micrometers, and preferably between 0.5 and 5 micrometers, on the electroplated or electroless plated nickel layer in the openings in the patterned photoresist layer, next removing the photoresist layer, next etching the seed layer of copper not under the copper layer **34**, and then etching the adhesion/barrier layer **32** not under the copper layer **34**. Accordingly, the metal pads, bumps or traces **34***a* provided by the adhesion/barrier layer **32**, the seed layer of copper, the copper layer **34**, the electroplated or electroless plated nickel layer and the electroplated or electroless plated gold layer can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The electroplated or electroless plated gold layer of the metal pad, bump or trace **34***a* can be used to be connected to the first external circuit by wirebonding a gold wire or a copper wire to the electroplated or electroless plated gold layer and to the first external circuit or by bonding the electroplated or electroless plated gold layer with a gold layer or a tin-alloy layer of the first external circuit.

[0625] Alternatively, the metal pads, bumps or traces **34***a* can be formed by a suitable process or processes, e.g., by a process including sputtering an adhesion/barrier layer **32**, such as titanium layer, titanium-tungsten-alloy layer, titanium-nitride layer, chromium layer, tantalum layer or tantalum-nitride layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, next sputtering a seed layer of copper (not shown) having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **32**, next forming a patterned photoresist layer on the seed layer of copper, and multiple openings in the patterned photoresist layer expose multiple regions of the seed layer of copper, next electroplating a copper layer **34** having a thickness larger than 1 micrometer, such as between 1 and 100 micrometers, and preferably between 5 and 60 micrometers, on the regions of the seed layer of copper exposed by the openings in the patterned photoresist layer, next electroplating or electroless plating a nickel layer (not shown) having a thickness between 0.5 and 8 micrometers, and preferably between 1 and 5 micrometers, on the copper layer **34** in the openings in the patterned photoresist layer, next electroplating a tin-containing layer (not shown), such as a tin-lead-alloy layer, a tin-silver-alloy layer or a tin-silver-copper-alloy layer, having a thickness between 1 and 150 micrometers, and preferably between 5 and 60 micrometers, on the electroplated or electroless plated nickel layer in the openings in the patterned photoresist layer, next removing the photoresist layer, next etching the seed layer of copper not under the copper layer **34**, and then etching the adhesion/barrier layer **32** not under the copper layer **34**. Accordingly, the metal pads, bumps or traces **34***a* provided by the adhesion/barrier layer **32**, the seed layer of copper, the copper layer **34**, the electroplated or electroless plated nickel layer and the electroplated tin-containing layer can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. The electroplated tin-containing layer of the metal pad, bump or trace **34***a* can be used to be connected to the first external circuit by bonding the electroplated tin-containing layer with a gold layer or a tin-alloy layer of the first external circuit.

[0626] After forming the metal pads, bumps or traces **34***a*, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18** and the metal bump or pillar **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**G-**25**L. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**L can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'** can be performed after forming the metal bump or pillar **27**.

[0627] After forming the structure shown in FIG. **25**N, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to the first external circuit through the metal pads, bumps or traces **34***a*, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bump or pillar **27** of the bottom scheme **103**.

[0628] FIG. **25**O is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, the patterned circuit layer **801** composed of the adhesion/barrier/seed layer **8011** and the metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, the polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and the opening **980** in the polymer layer **98** is over a contact point **801***a* of the metal layer **8012** of the patterned circuit layer **801** and exposes it, which can be referred to as the process illustrated in FIG. **15**I. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, a flux **32** is formed in the opening **980** and on the contact point **801***a* of the metal layer **8012** exposed by the opening **980**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18** and the metal bump or pillar **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**G-**25**L. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**L can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801**, the polymer layer **98** and the flux **32** can be performed after the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**L.

[0629] After forming the structure shown in FIG. **25**O, the flux **32** is removed. Thereafter, using a die-sawing process, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip. The semiconductor chip cut from the semiconductor wafer **10** can be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by wirebonding a gold wire or a copper wire to the contact point **801***a* of gold, copper or aluminum of the patterned circuit layer **801** of the over-passivation scheme **102** and to the first external circuit or by solder bonding the contact point **801***a* of the patterned circuit layer **801** of the over-passivation scheme **102** with a gold layer or a tin-alloy layer of the first external circuit, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bump or pillar **27** of the bottom scheme **103**.

[0630] FIG. **25**P is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. After the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**F are performed; the polymer layer **14** is formed on the bulk metal layer **9** and on the insulating layer **3**, and multiple openings **14***a* in the polymer layer **14** are over multiple regions of the bulk metal layer **9** and expose them, which can be referred to as the step illustrated in FIG. **25**G. Next, the adhesion/barrier layer **16** is formed on the polymer layer **14** and on the regions of the bulk metal layer **9** exposed by the openings **14***a*, and then the seed layer **18** is formed on the adhesion/barrier layer **16**, which can be referred to as the step illustrated in FIG. **25**H. Next, the photoresist layer **31** is formed on the seed layer **18**, and multiple openings **31***a* in the photoresist layer **31** expose the seed layer **18**, which can be referred to as the step illustrated in FIG. **25**I. Next, multiple metal bumps or pillars **27** are formed in the openings **31***a* and on the seed layer **18** exposed by the openings **31***a*, which can be referred to as the step illustrated in FIG. **25**J. Next, the photoresist layer **31** is removed, which can be referred to as the step illustrated in FIG. **25**K. Next, the seed layer **18** not under the metal bumps or pillars **27** is removed, and then the adhesion/barrier layer **16** not under the metal bumps or pillars **27** is removed, which can be referred to as the step illustrated in FIG. **25**L. Accordingly, the interconnecting structures **88** provided by the metal layers **4** and **9** can be formed in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, and the metal bumps or pillars **27** can be formed over the interconnecting structures **88** and at the backside **1***a* of the thinned silicon substrate **1**. The interconnecting structures **88** can connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and can connect the metal bumps or pillars **27** to the off-chip buffer **42** and to the internal circuits **21**, **22**, **23** and **24**. A bottom scheme **103**, shown in FIG. **25**P, at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the interconnecting structures **88** provided by the metal layers **4** and **9**, the polymer layer **14**, the metal layers **16** and **18**, and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the interconnecting structures **88**. After forming the structure shown in FIG. **25**P, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0631] Alternatively, after forming the structure shown in FIG. **25**P, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0632] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**L. After the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**L, the steps illustrated in FIG. **25**P is

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performed. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0633] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**, and the metal bumps or pillars **27** of the bottom scheme **103** of the semiconductor chip can be connected to the internal circuits **21**, **22**, **23** and **24** and the off-chip buffer **42** through the interconnecting structures **88** of the bottom scheme **103**.

[0634] FIG. **25**Q is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a flux **32** can be formed in the openings **531**, **532**, **534**, **539** and **539'** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the structure including the polymer layer **14** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIG. **25**P. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**P can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0635] After forming the structure shown in FIG. **25**Q, the flux **32** is removed. Next, with the following steps being illustrated with reverse figures for simple explanation, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**, and/or to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0636] FIG. **25**R is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, the metal pads, bumps or traces **34***a* can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the process illustrated in FIG. **25**N. The specification of the metal pads, bumps or traces **34***a* shown in FIG. **25**R can be referred to as the specification of the metal pads, bumps or traces **34***a* as illustrated in FIG. **25**N. After forming the metal pads, bumps or traces **34***a*, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the structure including the polymer layer **14** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIG. **25**P. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**P can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'** can be performed after forming the metal bumps or pillars **27**.

[0637] After forming the structure shown in FIG. **25**R, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, through the metal pads, bumps or traces **34***a*, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0638] FIG. **25**S is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and an opening **980** in the polymer layer **98** is over a contact point **801***a* of the metal layer **8012** of the patterned circuit layer **801** and exposes it, which can be referred to as the process illustrated in FIG. **15**I. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, a flux **32** is formed in the opening **980** and on the contact point **801***a* of the metal layer **8012** exposed by the opening **980**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the structure including the polymer layer **14** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIG. **25**P. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**P can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801** and the polymer layer **98** can be performed after forming the metal bumps or pillars **27**.

[0639] After forming the structure shown in FIG. **25**S, the flux **32** can be removed. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, by wirebonding a gold wire or a copper wire to the contact point **801***a* of gold, copper or aluminum of the patterned circuit layer **801** of the over-passivation scheme **102** and to the first external circuit or by solder bonding the contact point **801***a* of the patterned circuit layer **801** of the over-passivation scheme **102** with a gold layer or a tin-alloy layer of the first external circuit, and can be connected to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0640] FIG. **25**T is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**M. Next, multiple metal bumps **89** provided by the metal layers **89***a*, **89***b* and **89***c* can be formed on the polymer layer **98** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**, which can be referred to as the process illustrated in FIG. **15**M. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**. After forming the metal bumps **89**, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the structure including the polymer layer **14** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIG. **25**P. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**P can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801**, the polymer layer **98**, the metal layer **89***a* and the metal bumps **89** can be performed after forming the metal bumps or pillars **27**.

[0641] After forming the structure shown in FIG. **25**T, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal

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bumps **89** of the over-passivation scheme **102**, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**. The patterned circuit layer **801** connects the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connects the metal bumps **89** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0642] FIG. **25**U is a cross-sectional view showing a package, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**I. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, a flux can be formed in the openings **980** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0643] After forming the flux, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the polymer layer **14** can be formed on the bulk metal layer **9** of the interconnecting structures **88** and on the insulating layer **3**, and multiple openings **14***a* in the polymer layer **14** are over multiple regions of the bulk metal layer **9** and expose them, which can be referred to as the step illustrated in FIG. **25**G. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** can be formed with the insulating layer **3**, the interconnecting structures **88** provided by the metal layers **4** and **9**, and the polymer layer **14**, and the openings **14***a* in the polymer layer **14** are over the interconnecting structures **88**. Next, the flux is removed to expose the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0644] Alternatively, the step illustrated in FIG. **24**B can be performed before the steps of forming the patterned circuit layer **801** and the polymer layer **98**. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the interconnecting structures **88**, the polymer layer **14** and the openings **14***a* in the polymer layer **14** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**G. Next, the flux can be formed in the openings **14***a* and on the regions of the bulk metal layer **9** exposed by the openings **14***a*. Next, the patterned circuit layer **801**, the polymer layer **98** and the openings **980** in the polymer layer **98** can be formed at the active side of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**I. Next, the flux is removed to expose the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0645] After removing the flux, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. Thereafter, using a wire-bonding process, multiple wirebonded wires **129**, such as wirebonded gold wires or wirebonded copper wires, can be bonded onto the schemes **102** and **103** of the semiconductor chip cut from the semiconductor wafer **10**. For example, the wirebonded wires **129** can be wirebonded gold wires ball bonded with the regions of gold, copper, aluminum or palladium of the bulk metal layer **9** exposed by the openings **14***a* and with the regions **801***a* of gold, copper, aluminum or palladium of the metal layer **8012** exposed by the openings **980**. Alternatively, the wirebonded wires **129** can be wirebonded copper wires ball bonded with the regions of gold, copper, aluminum or palladium of the bulk metal layer **9** exposed by the openings **14***a* and with the regions **801***a* of gold, copper, aluminum or palladium of the metal layer **8012** exposed by the openings **980**.

[0646] FIG. **25**V is a cross-sectional view showing a package, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, the patterned circuit layer **801** composed of the adhesion/barrier/seed layer **8011** and the metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, the polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**I. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, a flux can be

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formed in the openings **980** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0647] After forming the flux, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, lib, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the structure including the polymer layer **14** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIG. **25**P. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **25**P can be formed at the backside **1***a* of the thinned silicon substrate **1**. Next, the flux is removed to expose the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0648] After removing the flux, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by wirebonding multiple wires **129**, such as gold wires or copper wires, to the regions **801***a* of the metal layer **8012** of the over-passivation scheme **102** and to the first external circuit, and can be connected to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by bonding the metal bumps or pillars **27** of the bottom scheme **103** with the second external circuit.

[0649] For example, using a wire-bonding process, the wirebonded wires **129** can be wirebonded gold wires ball bonded with the regions **801***a* of gold, copper, aluminum or palladium of the metal layer **8012** exposed by the openings **980**. Alternatively, using a wire-bonding process, the wirebonded wires **129** can be wirebonded copper wires ball bonded with the regions **801***a* of gold, copper, aluminum or palladium of the metal layer **8012** exposed by the openings **980**.

[0650] Alternatively, the step illustrated in FIG. **24**B can be performed before the steps of forming the patterned circuit layer **801** and the polymer layer **98**. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the structure including the polymer layer **14**, the openings **14***a* and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIG. **25**P. Next, the patterned circuit layer **801**, the polymer layer **98** and the openings **980** in the polymer layer **98** can be formed at the active side of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**I. Next, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. Thereafter, using a wire-bonding process, the wirebonded wires **129**, such as wirebonded gold wires or wirebonded copper wires, can be bonded onto the regions **801***a* of the metal layer **8012** exposed by the openings **980** of the semiconductor chip.

[0651] FIG. **25**W is a cross-sectional view showing a package, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, the patterned circuit layer **801** composed of the adhesion/barrier/seed layer **8011** and the metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, the polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**M. Next, multiple metal bumps **89** provided by the metal layers **89***a*, **89***b* and **89***c* can be formed on the polymer layer **98** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**, which can be referred to as the step illustrated in FIG. **15**M. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**.

[0652] After forming the metal bumps **89**, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the polymer layer **14** can be formed on the bulk metal layer **9** of the interconnecting structures **88** and on the insulating layer **3**, and multiple openings **14***a* in the polymer layer **14** are over multiple regions of the bulk metal layer **9** and expose them, which can be referred to as the step illustrated in FIG. **25**G. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the interconnecting structures **88** provided by the metal layers **4** and **9**, and the polymer layer **14**, and the openings **14***a* in the polymer layer **14** are over the interconnecting structures **88**. After forming the bottom scheme **103**, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0653] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package; the semiconductor chip can be connected to a first external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by bonding the metal bumps **89** of the over-passivation scheme **102** with the first external circuit, and can be connected to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by wire-bonding multiple wires **129**, such as gold wires or copper wires, to the bulk metal layer **9** of the bottom scheme **103** and to the second external circuit.

[0654] For example, using a wire-bonding process, the wirebonded wires **129** can be wirebonded gold wires ball bonded with the regions of gold, copper, aluminum or palladium of the bulk metal layer **9** exposed by the openings **14***a*. Alternatively, using a wire-bonding process, the wirebonded wires **129** can be wirebonded copper wires ball bonded with the regions of gold, copper, aluminum or palladium of the bulk metal layer **9** exposed by the openings **14***a*.

[0655] Alternatively, the step illustrated in FIG. **24**B can be performed before the steps of forming the patterned circuit layer **801**, the polymer layer **98** and the metal bumps **89**. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, lib, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the polymer layer **14** and the openings **14***a* in the polymer layer **14** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the step illustrated in FIG. **25**G Next, a flux can be formed in the openings **14***a* and on the regions of the bulk metal layer **9** exposed by the openings **14***a*. Next, the structure including the patterned circuit layer **801**, the polymer layer **98** and the metal bumps **89** can be formed at the active side of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H and **15**M. Next, the flux is removed. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, using a wire-bonding process, the wirebonded wires **129**, such as wirebonded gold wires or wirebonded copper wires, can be bonded onto the regions of the bulk metal layer **9** exposed by the openings **14***a* in the polymer layer **14** of the semiconductor chip.

[0656] FIGS. **26**A-**26**G are cross-sectional views showing a process for forming a bottom scheme **103** of a bottom structure technology at a backside of a semiconductor wafer according to the present disclosure. Referring to FIG. **26**A, after the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**D, a photoresist layer **51**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness between 1 and 200 micrometers, and preferably between 2 and 150 micrometers, can be formed on the photoresist layer **29** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a spin-on coating process, a screen-printing process, a lamination process or a spraying process. Next, the photoresist layer **51** is patterned with the processes of exposure and development to form multiple openings **51***a* in the photoresist layer **51** exposing multiple regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. For example, a 1× stepper or 1× contact aligner can be used to expose the photoresist layer **51** during the process of exposure. Each of the openings **51***a* has a desired width W**3**, e.g., larger than 5 micrometers, such as between 10 and 30 micrometers, between 20 and 50 micrometers or between 50 and 150 micrometers.

[0657] For example, the photoresist layer **51** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer having a thickness between 1 and 200 micrometers, and preferably between 2 and 150 micrometers, on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and on the photoresist layer **29**, then exposing the photosensitive polymer layer using a 1× stepper or a contact aligner with at least two of G-line, H-line and I-line, and G-line has a wavelength ranging from, e.g., about 434 to 438 nm, H-line has a wavelength ranging from, e.g., about 403 to 407 nm, and I-line has a wavelength ranging from, e.g., about 363 to 367 nm, then developing the exposed polymer layer by spraying and puddling a developer on the semiconductor wafer **10** or by immersing the semiconductor wafer **10** into a developer, and then cleaning the semiconductor wafer **10** using deionized wafer and drying the semiconductor wafer **10** by spinning the semiconductor wafer **10**. After development, a scum removal process of removing the residual polymeric material or other contaminants from the bulk metal layer **9** may be conducted by using an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By these processes, the photoresist layer **51** can be patterned with the openings **51***a* exposing the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**.

[0658] Referring to FIG. **26**B, after the step illustrated in FIG. **26**A, multiple metal bumps or pillars **27** having a thickness larger than 1 micrometer can be formed in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a*. The material of the metal bumps or pillars **27** may include gold, nickel, tin, solder, palladium, copper, aluminum or a composite of the previously described materials.

[0659] For example, the metal bumps or pillars **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**.

[0660] Alternatively, the metal bumps or pillars **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness between 1 and 30 micrometers, and preferably between 1 and 25 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**

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exposed by the openings **51***a* using the previously described electroplating solution for electroplating gold of the bulk metal layer **9**.

[0661] Alternatively, the metal bumps or pillars **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a palladium layer, to a thickness between 1 and 30 micrometers, and preferably between 1 and 25 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating palladium of the bulk metal layer **9**.

[0662] Alternatively, the metal bumps or pillars **27** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 1 and 100 micrometers, and preferably between 5 and 60 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating nickel of the bulk metal layer **9**.

[0663] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometer, in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0664] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometer, in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0665] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometer, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0666] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometer, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0667] Alternatively, the metal bumps or pillars **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0668] Alternatively, the metal bumps or pillars **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers,

in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0669] Alternatively, the metal bumps or pillars **27** can be composed of four metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, next electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **51***a* and on the electroplated or electroless plated palladium layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0670] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 250 micrometers, and preferably between 10 and 100 micrometer, in the openings **51***a* and on the electroplated copper layer in the openings **51***a*.

[0671] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 60 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 250 micrometers, and preferably between 10 and 100 micrometer, in the openings **51***a* and on the electroplated nickel layer in the openings **51***a*.

[0672] Alternatively, the metal bumps or pillars **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a*.

[0673] Alternatively, the metal bumps or pillars **27** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 10 micrometers, and preferably between 3 and 8 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***a* and on the electroplated copper layer in the openings **51***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 30 and 250 micrometers, and preferably between 50 and 150 micrometers, in the openings **51***a* and on the electroplated or electroless plated nickel layer in the openings **51***a*.

[0674] Alternatively, the metal bumps or pillars **27** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* using the previously described electroplating solution for electroplat-

ing copper of the bulk metal layer **9**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, in the openings **51***a* and on the electroplated copper layer in the openings **51***a*.

[0675] Referring to FIG. **26**C, after forming the metal bumps or pillars **27**, the photoresist layers **29** and **51** are removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layers **29** and **51** could remain on the seed layer **4***b* of the metal layer **4**, on the bulk metal layer **9** and on the metal bumps or pillars **27**. Thereafter, the residuals can be removed from the seed layer **4***b*, from the bulk metal layer **9** and from the metal bumps or pillars **27** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0676] Accordingly, the metal bumps or pillars **27** can be formed on the bulk metal layer **9** after the photoresist layers **29** and **51** are removed. Each of the metal bumps or pillars **27** has a width W**3** larger than 5 micrometers, such as between 10 and 30 micrometers, between 20 and 50 micrometers or between 50 and 150 micrometers, and larger than that of each of the fine-line metal layers **60**, and has a height H**1** larger than 1 micrometer, such as between 1 and 300 micrometers, between 5 and 250 micrometers, between 10 and 100 micrometers or between 5 and 50 micrometers. A pitch P**1** between neighboring two metal bumps or pillars **27** can be between 10 and 50 micrometers or between 50 and 200 micrometers. The metal bumps or pillars **27** can be used to be bonded with an external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, flexible substrate, metal substrate, glass substrate or ceramic substrate.

[0677] Alternatively, another process for forming the metal bumps or pillars **27** on the bulk metal layer **9** can be performed by the following steps. Referring to FIG. **26**D, after the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**D, the photoresist layer **29** can be removed using an inorganic solution or using an organic solution with amide. After removing the photoresist layer **29**, the photoresist layer **51** illustrated in FIG. **26**A can be formed on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and on the seed layer **4***b* of the metal layer **4** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **51** is patterned with the processes of exposure and development to form the openings **51***a* in the photoresist layer **51** exposing the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. Each of the openings **51***a* has a width W**3** larger than 5 micrometers, such as between 10 and 30 micrometers, between 20 and 50 micrometers or between 50 and 150 micrometers. The process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as shown in FIG. **26**D can be referred to as the process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as illustrated in FIG. **26**A.

[0678] Referring to FIG. **26**E, after the step illustrated in FIG. **26**D, the metal bumps or pillars **27** illustrated in FIG. **26**B are formed in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a*, which can be referred to as the step illustrated in FIG. **26**B. The specification of the metal bumps or pillars **27** shown in FIG. **26**E can be referred to as the specification of the metal bumps or pillars **27** illustrated in FIG. **26**B. After forming the metal bumps or pillars **27** as illustrated in FIG. **26**E, the photoresist layer **51** is removed using an inorganic solution or using an organic solution with amide. Accordingly, the metal bumps or pillars **27** can be formed on the bulk metal layer **9** after removing the photoresist layer **51**.

[0679] Referring to FIG. **26**F, after forming the metal bumps or pillars **27** on the bulk metal layer **9**, the metal layer **4** not under the bulk metal layer **9** is removed by etching the seed layer **4***b* not under the bulk metal layer **9**, and then etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**. The process of removing the seed layer **4***b* not under the bulk metal layer **9** and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as shown in FIG. **26**F can be referred to as the process of removing the seed layer **4***b* not under the bulk metal layer **9** and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as illustrated in FIG. **25**F.

[0680] Accordingly, the interconnecting structures **88** provided by the metal layer **4** and the bulk metal layer **9** can be formed in the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and sidewalls of the bulk metal layer **9** are not covered by the adhesion/barrier layer **4***a* and the seed layer **4***b* of the metal layer **4**. The interconnecting structures **88** connects the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, connects the off-chip buffer **42** to the metal bump or pillar **27**, and connects the internal circuits **21**, **22**, **23** and **24** to the metal bumps or pillars **27**. The off-chip ESD circuit **43** is connected to the off-chip buffer **42** through the fine-line metal trace **639**, and to the metal bump or pillar **27** through the interconnecting structure **88**.

[0681] Next, referring to FIG. **26**G, a polymer layer **14** is formed on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** of the interconnecting structures **88**, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and multiple openings **14***a* are formed in the polymer layer **14** to uncover the top surfaces and the sidewalls of the metal bumps or pillars **27**. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the interconnecting structures **88** provided by the metal layers **4** and **9**, the metal bumps or pillars **27**, and the polymer layer **14**, and the openings **14***a* in the polymer layer **14** are over the interconnecting structures **88**. After the step illustrated in FIG. **26**G, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0682] Alternatively, after the step illustrated in FIG. **26**G, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0683] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-

15M, 16L, 16M, 17J, 18I, 19H and 20 over the passivation layer 5 can be performed before the steps illustrated in FIGS. 24B, 24C, 25A-25D and 26A-26G. After the steps illustrated in FIGS. 24B, 24C, 25A-25D and 26A-26G, the semiconductor wafer 10 can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0684] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer 10 can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars 27 of the bottom scheme 103. The semiconductor chip includes the bottom scheme 103, and the bottom scheme 103 includes the insulating layer 3 on the backside 1*a* of the thinned silicon substrate 1 and in the through-silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e*, the interconnecting structures 88 at the backside 1*a* of the thinned silicon substrate 1, in the through-silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e* and on the insulating layer 3, the polymer layer 14 at the backside 1*a* of the thinned silicon substrate 1, on the interconnecting structures 88 and on the insulating layer 3, and the metal bumps or pillars 27 at the backside 1*a* of the thinned silicon substrate 1 and on the interconnecting structures 88.

[0685] FIG. 26H is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer 10 illustrated in FIG. 24A includes multiple openings 531, 532, 534, 539 and 539' in the passivation layer 5 to expose multiple regions 600*a* of the metal traces or pads 600. The openings 531, 532, 534, 539 and 539' are over the regions 600*a* of the metal traces or pads 600, and the regions 600*a* of the metal traces or pads 600 are at bottoms of the openings 531, 532, 534, 539 and 539'. Next, a flux 32 can be formed in the openings 531, 532, 534, 539 and 539' and on the regions 600*a* of the metal traces or pads 600 exposed by the openings 531, 532, 534, 539 and 539'. Next, the step illustrated in FIG. 24B can be performed. Next, the through silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e* can be formed in the thinned silicon substrate 1, and the insulating layer 3 can be formed on the backside 1*a* of the thinned silicon substrate 1 and on the sidewalls of the through silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e*, which can be referred to as the steps illustrated in FIGS. 24C-24H or FIGS. 24I-24N. Next, the interconnecting structures 88 can be formed in the through silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e*, on the insulating layer 3 and at the backside 1*a* of the thinned silicon substrate 1, and the metal bumps or pillars 27 can be formed on the interconnecting structures 88, which can be referred to as the steps illustrated in FIGS. 25A-25D and 26A-26F. Next, the polymer layer 14 is formed on the interconnecting structures 88, on the insulating layer 3 and at the backside 1*a* of the thinned silicon substrate 1, and the openings 14*a* are formed in the polymer layer 14 to uncover the top surfaces and the sidewalls of the metal bumps or pillars 27. Accordingly, a bottom scheme 103 same as the bottom scheme 103 shown in FIG. 26G can be formed at the backside 1*a* of the thinned silicon substrate 1.

[0686] After forming the structure shown in FIG. 26H, the flux 32 is removed. Next, with the following steps being illustrated with reverse figures for simple explanation, each of the over-passivation schemes 102 illustrated in FIGS. 15H, 15K-15M, 16L, 16M, 17J, 18I, 19H and 20 can be alternatively formed over the passivation layer 5 at the active side of the thinned silicon substrate 1. Thereafter, the semiconductor wafer 10 can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer 10 can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars 27 of the bottom scheme 103, and/or to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through one of the over-passivation schemes 102 illustrated in FIGS. 15H, 15K-15M, 16L, 16M, 17J, 18I, 19H and 20. The interconnecting structures 88 connect the off-chip buffer 42 to the internal circuits 21, 22, 23 and 24, and connect the metal bumps or pillars 27 to the off-chip buffer 42, to the off-chip ESD circuit 43 and to the internal circuits 21, 22, 23 and 24.

[0687] FIG. 26I is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer 10 illustrated in FIG. 24A includes multiple openings 531, 532, 534, 539 and 539' in the passivation layer 5 to expose multiple regions 600*a* of the metal traces or pads 600. The openings 531, 532, 534, 539 and 539' are over the regions 600*a* of the metal traces or pads 600, and the regions 600*a* of the metal traces or pads 600 are at bottoms of the openings 531, 532, 534, 539 and 539'. Next, the metal pads, bumps or traces 34*a* can be formed on the passivation layer 5 and on the regions 600*a* of the metal traces or pads 600 exposed by the openings 531, 532, 534, 539 and 539', which can be referred to as the process illustrated in FIG. 25N. The specification of the metal pads, bumps or traces 34*a* shown in FIG. 26I can be referred to as the specification of the metal pads, bumps or traces 34*a* as illustrated in FIG. 25N. After forming the metal pads, bumps or traces 34*a*, the step illustrated in FIG. 24B can be performed. Next, the through silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e* can be formed in the thinned silicon substrate 1, and the insulating layer 3 can be formed on the backside 1*a* of the thinned silicon substrate 1 and on the sidewalls of the through silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e*, which can be referred to as the steps illustrated in FIGS. 24C-24H or FIGS. 24I-24N. Next, the interconnecting structures 88 can be formed in the through silicon vias 11*a*, 11*b*, 11*c*, 11*d* and 11*e*, on the insulating layer 3 and at the backside 1*a* of the thinned silicon substrate 1, and the metal bumps or pillars 27 can be formed on the interconnecting structures 88, which can be referred to as the steps illustrated in FIGS. 25A-25D and 26A-26F. Next, the polymer layer 14 is formed on the interconnecting structures 88, on the insulating layer 3 and at the backside 1*a* of the thinned silicon substrate 1, and the openings 14*a* are formed in the polymer layer 14 to uncover the top surfaces and the sidewalls of the metal bumps or pillars 27. Accordingly, a bottom scheme 103 same as the bottom scheme 103 shown in FIG. 26G can be formed at the backside 1*a* of the thinned silicon substrate 1. Alternatively, the step of forming the metal pads, bumps or traces 34*a* on the passivation layer 5 and on the regions 600*a* of the metal traces or pads 600 exposed by the openings 531, 532, 534, 539 and 539' can be performed after forming the polymer layer 14.

[0688] After forming the structure shown in FIG. 26I, the semiconductor wafer 10 can be cut into a plurality of indi-

vidual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, through the metal pads, bumps or traces **34***a*, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0689] FIG. **26**J is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and an opening **980** in the polymer layer **98** is over a contact point **801***a* of the metal layer **8012** of the patterned circuit layer **801** and exposes it, which can be referred to as the process illustrated in FIG. **15**I. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, a flux **32** is formed in the opening **980** and on the contact point **801***a* of the metal layer **8012** exposed by the opening **980**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the metal bumps or pillars **27** can be formed on the interconnecting structures **88**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**D and **26**A-**26**F. Next, the polymer layer **14** is formed on the interconnecting structures **88**, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the openings **14***a* are formed in the polymer layer **14** to uncover the top surfaces and the sidewalls of the metal bumps or pillars **27**. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **26**G can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801** and the polymer layer **98** can be performed after forming the polymer layer **14**.

[0690] After forming the structure shown in FIG. **26**J, the flux **32** is removed. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, by wirebonding a gold wire or a copper wire to the contact point **801***a* of gold, copper or aluminum of the patterned circuit layer **801** and to the first external circuit or by solder bonding the contact point **801***a* of the patterned circuit layer **801** with a gold layer or a tin-alloy layer of the first external circuit, and can be connected to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0691] FIG. **26**K is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, and multiple metal bumps or pillars **141** can be formed on multiple regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012** of the patterned circuit layer **801**. The adhesion/barrier/seed layer **8011** is formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, and the metal layer **8012** is formed on the adhesion/barrier/seed layer **8011**. After forming the metal bumps or pillars **141**, a polymer layer **98** can be formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** are formed in the polymer layer **98** to uncover top surfaces and sidewalls of the metal bumps or pillars **141**. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801**, the metal bumps or pillars **141** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias

11*a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the metal bumps or pillars **27** can be formed on the interconnecting structures **88**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**D and **26**A-**26**F. Next, the polymer layer **14** is formed on the interconnecting structures **88**, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the openings **14***a* are formed in the polymer layer **14** to uncover the top surfaces and the sidewalls of the metal bumps or pillars **27**. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **26**G can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801**, the metal bumps or pillars **141** and the polymer layer **98** can be performed after forming the polymer layer **14**.

[0692] The metal bumps or pillars **141** have a width larger than 3 micrometers, such as between 5 and 100 micrometers, and a height grater than 1 micrometer, such as between 5 and 150 micrometers or between 10 and 100 micrometers. The material of the metal bumps or pillars **141** may include gold, copper, nickel, aluminum, palladium, solder or a composite of the previously described materials. The metal bumps or pillars **141** can be used to be bonded with an external circuit, such as printed circuit board, flexible substrate, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate.

[0693] The metal bumps or pillars **141**, for example, can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 100 micrometers, between 10 and 150 micrometers or between 20 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**.

[0694] Alternatively, the metal bumps or pillars **141** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness between 1 and 30 micrometers, between 10 and 25 micrometers or between 3 and 50 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**.

[0695] Alternatively, the metal bumps or pillars **141** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a palladium layer, to a thickness between 1 and 30 micrometers, between 10 and 25 micrometers or between 3 and 50 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**.

[0696] Alternatively, the metal bumps or pillars **141** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 5 and 100 micrometers, and preferably between 10 and 60 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**.

[0697] Alternatively, the metal bumps or pillars **141** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 100 micrometers, between 10 and 150 micrometers or between 20 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, on the electroplated copper layer.

[0698] Alternatively, the metal bumps or pillars **141** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, on the electroplated or electroless plated nickel layer.

[0699] Alternatively, the metal bumps or pillars **141** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, on the electroplated or electroless plated nickel layer.

[0700] Alternatively, the metal bumps or pillars **141** can be composed of four metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer, next electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, on the electroplated or electroless plated nickel layer, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, on the electroplated or electroless plated palladium layer.

[0701] Alternatively, the metal bumps or pillars **141** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometer, on the electroplated copper layer.

[0702] Alternatively, the metal bumps or pillars **141** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between

5 and 250 micrometers, and preferably between 10 and 100 micrometer, on the electroplated nickel layer.

[0703] Alternatively, the metal bumps or pillars **141** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, on the electroplated or electroless plated nickel layer.

[0704] Alternatively, the metal bumps or pillars **141** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 10 micrometers, and preferably between 3 and 8 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 30 and 250 micrometers, and preferably between 50 and 150 micrometers, on the electroplated or electroless plated nickel layer.

[0705] Alternatively, the metal bumps or pillars **141** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the regions of gold, copper, nickel, aluminum or palladium of the metal layer **8012**, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, on the electroplated copper layer.

[0706] After forming the structure shown in FIG. **26**K, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **141** of the over-passivation scheme **102**, and can be connected to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The patterned circuit layer **801** composed of the metal layers **8011** and **8012** at the active side of the thinned silicon substrate **1** connects the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connects the off-chip buffer **42** and the internal circuits **21**, **22**, **23** and **24** to the first external circuit through the metal bumps or pillars **141**. The interconnecting structures **88** provided by the metal layers **4** and **9** at the backside **1***a* of the thinned silicon substrate **1** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the off-chip buffer **42** and the internal circuits **21**, **22**, **23** and **24** to the second external circuit through the metal bumps or pillars **27**. The off-chip ESD circuit **43** can be connected to the patterned circuit layer **801** through the fine-line metal trace **639**, and to the interconnecting structure **88** through the fine-line metal trace **639**.

[0707] FIGS. **27**A-**27**Q are cross-sectional views showing a process for forming a bottom scheme **103** of a bottom structure technology at a backside of a semiconductor wafer according to the present disclosure. Referring to FIG. **27**A, after the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**D, a photoresist layer **51**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 120 micrometers, and preferably between 5 and 50 micrometers, can be formed on the photoresist layer **29** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **51** is patterned with the processes of exposure and development to form multiple openings **51***b* in the photoresist layer **51** exposing multiple regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **51** during the process of exposure. Each of the openings **51***b* has a width W**4** between 3 and 10 micrometers or between 10 and 30 micrometers. The process of forming the photoresist layer **51** and the openings **51***b* in the photoresist layer **51** as shown in FIG. **27**A can be referred to as the process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as illustrated in FIG. **26**A.

[0708] Next, referring to FIG. **27**B, multiple via plugs **58** can be formed in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b*. The material of the via plugs **58** may include gold, nickel, tin, palladium, silver, aluminum, copper or a composite of the previously described materials.

[0709] For example, the via plugs **58** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 100 micrometers, and preferably between 2 and 30 micrometers, in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**.

[0710] Alternatively, the via plugs **58** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating or electroless plating a gold layer, to a thickness between 1 and 100 micrometers, and preferably between 2 and 30 micrometers, in the openings **51***b* and on the regions **9***a* of the topmost layer of copper; gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0711] Alternatively, the via plugs **58** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating or electroless plating a palladium layer, to a thickness between 1 and 100 micrometers, and preferably between 2 and 30 micrometers, in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0712] Alternatively, the via plugs **58** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating or electroless plating a nickel layer, to a thickness between 1 and 100 micrometers, and preferably between 2 and 30 micrometers, in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**.

[0713] Alternatively, the via plugs **58** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 100 micrometers, and preferably between 2 and 30 micrometers, in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometer, in the openings **51***b* and on the electroplated copper layer in the openings **51***b*.

[0714] Alternatively, the via plugs **58** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometer, in the openings **51***b* and on the electroplated or electroless plated nickel layer in the openings **51***b*.

[0715] Referring to FIG. **27**C, after forming the via plugs **58**, the photoresist layers **29** and **51** are removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layers **29** and **51** could remain on the bulk metal layer **9** and on the via plugs **58**. Thereafter, the residuals can be removed from the bulk metal layer **9** and from the via plugs **58** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. Accordingly, the via plugs **58** can be formed on the bulk metal layer **9** after the photoresist layers **29** and **51** are removed. Each of the via plugs **58** has a width W**4** between 3 and 10 micrometers or between 10 and 30 micrometers, and a height between 1 and 100 micrometers, and preferably between 2 and 30 micrometers.

[0716] Alternatively, another process for forming the via plugs **58** on the bulk metal layer **9** can be performed by the following steps. Referring to FIG. **27**D, after the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**D, the photoresist layer **29** can be removed using an inorganic solution or using an organic solution with amide. After the photoresist layer **29** is removed, the previously described photoresist layer **51** having a thickness between 1 and 120 micrometers, and preferably between 5 and 50 micrometers, can be formed on the seed layer **4***b* of the metal layer **4** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **51** is patterned with the processes of exposure and development to form the openings **51***b* in the photoresist layer **51** exposing the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. The process of forming the photoresist layer **51** and the openings **51***b* in the photoresist layer **51** as shown in FIG. **27**D can be referred to as the process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as illustrated in FIG. **26**A.

[0717] Referring to FIG. **27**E, after the step illustrated in FIG. **27**D, the via plugs **58** illustrated in FIG. **27**B are formed in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b*. The process of forming the via plugs **58** in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** as shown in FIG. **27**E can be referred to as the process of forming the via plugs **58** in the openings **51***b* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***b* as illustrated in FIG. **27**B. The specification of the via plugs **58** shown in FIG. **27**E can be referred to as the specification of the via plugs **58** illustrated in FIG. **27**B. After forming the via plugs **58**, the photoresist layer **51** is removed using an inorganic solution or using an organic solution with amide. Accordingly, the via plugs **58** can be formed on the bulk metal layer **9** after the photoresist layer **51** is removed.

[0718] Referring to FIG. **27**F, after forming the via plugs **58** on the bulk metal layer **9**, the metal layer **4** not under the bulk metal layer **9** is removed with an etching method. The process of removing the metal layer **4** not under the bulk metal layer **9** shown in FIG. **27**F can be referred to as the process of removing the metal layer **4** not under the bulk metal layer **9** as illustrated in FIG. **25**F. Accordingly, multiple interconnecting structures **88** provided by the metal layer **4** and the bulk metal layer **9** can be formed in the thinned silicon substrate **1** and at the backside **1***a* of the thinned silicon substrate **1**, and sidewalls of the bulk metal layer **9** are not covered by the metal layer **4**. The interconnecting structures **88** can connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24** and connect the off-chip buffer **42** to the via plug **58**.

[0719] Next, referring to FIG. **27**G, a polymer layer **142** can be formed on the insulating layer **3**, on the via plugs **58** and on the bulk metal layer **9**, enclosing the via plugs **58** and the bulk metal layer **9**, by a spin-on coating process, a lamination process or a screen-printing process. The polymer layer **142**

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has a thickness t**6** between 10 and 200 micrometers, and preferably between 15 and 50 micrometers. The material of the polymer layer **142** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0720] For example, the polymer layer **142** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer, containing ester-type precursor, having a thickness between 20 and 400 micrometers, and preferably between 30 and 100 micrometers on the insulating layer **3**, on the via plugs **58** and on the bulk metal layer **9**, then baking the spin-on coated polyimide layer, and then curing or heating the baked polyimide layer at a temperature between 180 and 400° C., between 180 and 250° C., between 250 and 290° C., between 290 and 400° C. or between 200 and 390° C. for a time between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness between 10 and 200 micrometers, and preferably between 15 and 50 micrometers. By the way, the polymer layer **142** can be formed on the insulating layer **3**, on the via plugs **58** and on the bulk metal layer **9**, and encloses the via plugs **58** and the bulk metal layer **9**.

[0721] Referring to FIG. **27**H, after forming the polymer layer **142**, a polishing or mechanical polishing process, and preferably a chemical-mechanical polishing (CMP) process, is used to planarize the surface of the polymer layer **142**, exposing the via plugs **58**. The polymer layer **142**, after being planarized, may have a thickness t**7** between 7 and 80 micrometers, and preferably between 10 and 30 micrometers. The top surfaces **58***a* of the via plugs **58** can be substantially coplanar with the top surface **142***a* of the polymer layer **142**.

[0722] Next, referring to FIG. **27**I, an adhesion/barrier layer **64** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the top surface **142***a* of the polymer layer **142** and on the top surfaces **58***a* of the via plugs **58** by a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **65** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **64** by a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **64** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **65** may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0723] For example, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy; titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the top surface **142***a* of the polymer layer **142** and on the top surfaces **58***a* of the via plugs **58**, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0724] Alternatively, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the top surface **142***a* of the polymer layer **142** and on the top surfaces **58***a* of the via plugs **58** and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-tungsten-alloy layer.

[0725] Alternatively, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the top surface **142***a* of the polymer layer **142** and on the top surfaces **58***a* of the via plugs **58**, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0726] Alternatively, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the top surface **142***a* of the polymer layer **142** and on the top surfaces **58***a* of the via plugs **58**, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0727] Referring to FIG. **27**J, after forming the seed layer **65**, a photoresist layer **67**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1 micrometer, such as between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, is formed on the seed layer **65** of any previously described material by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **67** is patterned with the processes of exposure and development to form multiple openings **67***a* in the photoresist layer **67** exposing the seed layer **65** of any previously described material. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **67** during the process of exposure.

[0728] For example, the photoresist layer **67** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polymer layer having a thickness between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, on the seed layer **65**, then exposing

the photosensitive polymer layer using a 1× stepper or a contact aligner with at least two of G-line, H-line and I-line, and G-line has a wavelength ranging from, e.g., about 434 to 438 nm, H-line has a wavelength ranging from, e.g., about 403 to 407 nm, and I-line has a wavelength ranging from, e.g., about 363 to 367 nm, then developing the exposed polymer layer by spraying and puddling a developer on the semiconductor wafer **10** or by immersing the semiconductor wafer **10** into a developer, and then cleaning the semiconductor wafer **10** using deionized wafer and drying the semiconductor wafer **10** by spinning the semiconductor wafer **10**. After development, a scum removal process of removing the residual polymeric material or other contaminants from the seed layer **65** may be conducted by using an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By these processes, the photoresist layer **67** can be patterned with the openings **67***a* exposing the seed layer **65**.

[0729] Next, referring to FIG. **27**K, a metal layer **68** having a thickness larger than 1 micrometer, such as between 1 and 50 micrometers, and preferably between 2 and 20 micrometers, can be electroplated in the openings **67***a* and on the seed layer **65** of any previously described material exposed by the openings **67***a*. The metal layer **68** may be a single layer of gold, copper, silver, palladium, platinum, rhodium, ruthenium, rhenium or nickel, or a composite layer made of the previously described metals.

[0730] For example, the metal layer **68** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 20 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described gold layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating gold of the bulk metal layer **9**.

[0731] Alternatively, the metal layer **68** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 20 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described copper layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**.

[0732] Alternatively, the metal layer **68** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a palladium layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 20 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described palladium layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating palladium of the bulk metal layer **9**.

[0733] Alternatively, the metal layer **68** can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 20 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described copper layer or nickel layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating nickel of the bulk metal layer **9**.

[0734] Alternatively, the metal layer **68** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 15 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described copper layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, in the openings **67***a* and on the electroplated copper layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0735] Alternatively, the metal layer **68** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 15 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described copper layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, in the openings **67***a* and on the electroplated copper layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0736] Alternatively, the metal layer **68** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 15 micrometers, on the seed layer **65**, preferably the previously described copper layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, and then electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 5 micrometers, in the openings **67***a* and on the electroplated copper layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**.

[0737] Alternatively, the metal layer **68** can be composed of double metal layers formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 15 micrometers, in the openings **67***a* and on the seed layer **65**, preferably the previously described copper layer or nickel layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, in the openings **67***a* and on the electroplated nickel layer in the openings **67***a*.

[0738] Alternatively, the metal layer **68** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 15 micrometers, on the seed layer **65**, preferably the previously described copper layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and

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15 micrometers, and preferably between 2 and 5 micrometers, in the openings **67***a* and on the electroplated copper layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a gold layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **67***a* and on the electroplated or electroless plated nickel layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating gold of the bulk metal layer **9**.

[0739] Alternatively, the metal layer **68** can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness between 1 and 50 micrometers, and preferably between 2 and 15 micrometers, on the seed layer **65**, preferably the previously described copper layer **65**, exposed by the openings **67***a* using the previously described electroplating solution for electroplating copper of the bulk metal layer **9**, next electroplating or electroless plating a nickel layer, to a thickness between 1 and 15 micrometers, and preferably between 2 and 5 micrometers, in the openings **67***a* and on the electroplated copper layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating nickel of the bulk metal layer **9**, and then electroplating or electroless plating a palladium layer, to a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, in the openings **67***a* and on the electroplated or electroless plated nickel layer in the openings **67***a* using the previously described electroplating or electroless plating solution for electroplating or electroless plating palladium of the bulk metal layer **9**.

[0740] Referring to FIG. **27**L, after forming the metal layer **68**, the photoresist layer **67** can be removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **67** could remain on the metal layer **68** and on the seed layer **65** not under the metal layer **68**. Thereafter, the residuals can be removed from the metal layer **68** and from the seed layer **65** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0741] Next, referring to FIG. **27**M, the seed layer **65** and the adhesion/barrier layer **64** not under the metal layer **68** are subsequently removed with an etching method. In a case, the seed layer **65** and the adhesion/barrier layer **65** not under the metal layer **68** can be subsequently removed by a dry etching method. As to the dry etching method, both the seed layer **65** and the adhesion/barrier layer **64** not under the metal layer **68** can be subsequently removed by an Ar sputtering etching process; alternatively, both the seed layer **65** and the adhesion/barrier layer **64** not under the metal layer **68** can be subsequently removed by a reactive ion etching (RIE) process; alternatively, the seed layer **65** not under the metal layer **68** can be removed by an Ar sputtering etching process, and then the adhesion/barrier layer **64** not under the metal layer **68** can be removed by a reactive ion etching (RIE) process. In another case, the seed layer **65** and the adhesion/barrier layer **64** not under the metal layer **68** can be subsequently removed by a wet etching method. As to the wet etching method, when the seed layer **65** is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4; when the adhesion/barrier layer **64** is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide; when the adhesion/barrier layer **64** is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide; when the adhesion/barrier layer **64** is a chromium layer, it can be etched with a solution containing potassium ferricyanide. In another case, the seed layer **65**, such as copper, not under the metal layer **68** can be removed by a solution containing NH_4OH or a solution containing H_2SO_4, and then the adhesion/barrier layer **64** not under the metal layer **68** can be removed by a reactive ion etching (RIE) process. In another case, the seed layer **65**, such as copper, not under the metal layer **68** can be removed by a solution containing NH_4OH or a solution containing H_2SO_4, and, then the adhesion/barrier layer **64** not under the metal layer **68** can be removed by an Ar sputtering etching process.

[0742] Next, referring to FIG. **27**N, a polymer layer **14** can be formed on the top surface **142***a* of the polymer layer **142** and on the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and multiple openings **14***a* in the polymer layer **14** are over multiple regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** and expose them. The polymer layer **14** has a thickness larger than 2 micrometers, such as between 3 and 50 micrometers, and preferably between 5 and 25 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0743] In a case, the polymer layer **14** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer having a thickness between 6 and 100 micrometers on the top surface **142***a* of the polymer layer **142** and on the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or a 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form multiple openings exposing the metal layer **68**, then curing or heating the developed polyimide layer at a temperature between 180 and 400° C., between 180 and 250° C., between 250 and 290° C., between 290 and 400° C. or between 200 and 390° C. for a time between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness between 3 and 50 micrometers, and then removing the residual polymeric material or other contaminants from the metal layer **68** exposed by the openings **14***a* with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By the way, the polymer layer **14** can be formed on the top surface **142***a* of the polymer layer **142** and on the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68**, and the openings **14***a* formed in the polymer layer **14**

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expose the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68**.

[0744] In another case, the polymer layer **14** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polybenzoxazole layer having a thickness between 3 and 50 micrometers on the top surface **142***a* of the polymer layer **142** and on the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68**, then baking the spin-on coated polybenzoxazole layer, then exposing the baked polybenzoxazole layer using a 1× stepper or a 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polybenzoxazole layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polybenzoxazole layer, then developing the exposed polybenzoxazole layer to multiple openings exposing the metal layer **68**, then curing or heating the developed polybenzoxazole layer at a temperature between 150 and 250° C., and preferably between 180 and 250° C., or between 200 and 400° C., and preferably between 250 and 350° C., for a time between 5 and 180 minutes, and preferably between 30 and 120 minutes, in a nitrogen ambient or in an oxygen-free ambient, the cured polybenzoxazole layer having a thickness between 3 and 50 micrometers, and then removing the residual polymeric material or other contaminants from the metal layer **68** exposed by the openings **14***a* with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By the way, the polymer layer **14** can be formed on the top surface **142***a* of the polymer layer **142** and on the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68**, and the openings **14***a* formed in the polymer layer **14** expose the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68**.

[0745] Next, referring to FIG. **27**O, an adhesion/barrier layer **16** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **14** and on the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the openings **14***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **18** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **16** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **16** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **18** may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0746] For example, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14** and on the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the openings **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0747] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the polymer layer **14** and on the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the openings **14***a* and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-tungsten-alloy layer.

[0748] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14** and on the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the openings **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0749] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14** and on the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the openings **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0750] Referring to FIG. **27**P, after the step illustrated in FIG. **27**O, a photoresist layer **31** can be formed on the seed layer **18** of any previously described material, and multiple openings **31***a* in the photoresist layer **31** expose the seed layer **18** of any previously described material, which can be referred to as the step illustrated in FIG. **25**I. Next, multiple

metal bumps or pillars **27** can be formed on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a*. The process of forming the metal bumps or pillars **27** on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a* as shown in FIG. **27**P can be referred to as the process of forming the metal bump or pillar **27** on the seed layer **18** of any previously described material exposed by the opening **31***a* and in the opening **31***a* as illustrated in FIG. **25**J. The specification of the metal bumps or pillars **27** shown in FIG. **27**P can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J.

[0751] Next, referring to FIG. **27**Q, the photoresist layer **31** is removed, which can be referred to as the step illustrated in FIG. **25**K. Next, the seed layer **18** not under the metal bumps or pillars **27** is removed, and then the adhesion/barrier layer **16** not under the metal bumps or pillars **27** is removed, which can be referred to as the step illustrated in FIG. **25**L. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the interconnecting structures **88** provided by the metal layers **4** and **9**, the via plugs **58**, the polymer layers **14** and **142**, the metal layers **16**, **18**, **64**, **65** and **68**, and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the metal layer **68**. After the step illustrated in FIG. **27**Q, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0752] Alternatively, after the step illustrated in FIG. **27**Q, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0753] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **24**B, **24**C, **25**A-**25**D and **27**A-**27**Q. After the steps illustrated in FIGS. **24**B, **24**C, **25**A-**25**D and **27**A-**27**Q, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0754] After the die-awing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The metal bumps or pillars **27** of the semiconductor chip can be connected to the off-chip buffer **42**, the off-chip ESD circuit **43** and the internal circuits **21**, **22**, **23** and **24** through the metal layer **68**, the via plugs **58** and the bulk metal layer **9**. Multiple interconnecting structures provided by the metal layer **4**, the bulk metal layer **9**, the via plugs **58**, the adhesion/barrier layer **64**, the seed layer **65** and the metal layer **68** can be formed at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor chip, and the interconnecting structures can connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24** and can connect the off-chip buffer **42** and the internal circuits **21**, **22**, **23** and **24** to the external circuit through the metal bumps or pillars **27**.

[0755] FIG. **27**R is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a flux **32** can be formed in the openings **531**, **532**, **534**, **539** and **539'** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the via plugs **58** can be formed on the interconnecting structures **88** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**D and **27**A-**27**F. Next, the polymer layers **142** and **14**, the adhesion/barrier layers **16** and **64**, the seed layers **18** and **65**, the metal layer **68** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **27**G-**27**Q. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **27**Q can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0756] After forming the structure shown in FIG. **27**R, the flux **32** is removed. Next, with the following steps being illustrated with reverse figures for simple explanation, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**, and/or to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20**.

[0757] FIG. **27**S is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes,.e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the

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regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, the metal pads, bumps or traces **34***a* can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the process illustrated in FIG. **25**N. The specification of the metal pads, bumps or traces **34***a* shown in FIG. **27**S can be referred to as the specification of the metal pads, bumps or traces **34***a* as illustrated in FIG. **25**N. After forming the metal pads, bumps or traces **34***a*, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the via plugs **58** can be formed on the interconnecting structures **88** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**D and **27**A-**27**F. Next, the polymer layers **142** and **14**, the adhesion/barrier layers **16** and **64**, the seed layers **18** and **65**, the metal layer **68** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **27**G-**27**Q. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **27**Q can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'** can be performed after forming the metal bumps or pillars **27**.

[0758] After forming the structure shown in FIG. **27**S, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, through the metal pads, bumps or traces **34***a*, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**.

[0759] FIG. **27**T is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**M. Next, multiple metal bumps **89** provided by the metal layers **89***a*, **89***b* and **89***c* can be formed on the polymer layer **98** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**, which can be referred to as the process illustrated in FIG. **15**M. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**. After forming the metal bumps **89**, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the via plugs **58** can be formed on the interconnecting structures **88** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**D and **27**A-**27**F. Next, the polymer layers **142** and **14**, the adhesion/barrier layers **16** and **64**, the seed layers **18** and **65**, the metal layer **68** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **27**G-**27**Q. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **27**Q can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801**, the polymer layer **98**, the metal layer **89***a* and the metal bumps **89** can be performed after forming the metal bumps or pillars **27**.

[0760] After forming the structure shown in FIG. **27**T, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps **89** of the over-passivation scheme **102**, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**.

[0761] FIGS. **28**A-**28**F are cross-sectional views showing a process for forming a bottom scheme **103** of a bottom structure technology at a backside of a semiconductor wafer according to the present disclosure. Referring to FIG. **28**A, after the steps illustrated in FIGS. **24**B, **24**C and **25**A-**25**F, an insulating layer **46** having a thickness t**8** larger than 0.1 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers, can be formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described

various bulk metal layer **9** by using a chemical vapor deposition (CVD) process. The insulating layer **46** can be a single layer of silicon oxide, silicon oxynitride or silicon nitride (such as Si_3N_4), a composite layer made of previously described materials.

[0762] For example, the insulating layer **46** can be an inorganic layer, such as silicon-oxide layer, silicon-oxynitride layer or silicon-nitride layer, having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers, on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. Alternatively, the insulating layer **46** can be an insulating nitride layer, such as silicon-nitride layer or silicon-oxynitride layer, having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers, on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. Alternatively, the insulating layer **46** can be an oxide layer, such as silicon-oxide layer or silicon-oxynitride layer, having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers, on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. Alternatively, the insulating layer **46** can be composed of double layers including an insulating nitride layer, such as silicon-nitride layer or silicon-oxynitride layer, having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers, on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, and an oxide layer, such as silicon-oxide layer or silicon-oxynitride layer, having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers, and preferably between 0.3 and 1 micrometers, on the insulating nitride layer.

[0763] Referring to FIG. **28**B, after forming the insulating layer **46**, a polymer layer **14** can be formed on the insulating layer **46** using a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process, and multiple openings **14***a* in the polymer layer **14** expose multiple regions of the insulating layer **46** over the bulk metal layer **9**. The polymer layer **14** has a thickness between 3 and 50 micrometers, and preferably between 5 and 25 micrometers, and the polymer layer **14** can be a single layer of benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin. The process of forming the polymer layer **14** and the openings **14***a* in the polymer layer **14** as shown in FIG. **28**B can be referred to as the process of forming the polymer layer **14** and the opening **14***a* in the polymer layer **14** as illustrated in FIG. **25**G.

[0764] Referring to FIG. **28**C, after the step illustrated in FIG. **28**B, the regions of the insulating layer **46** exposed by the openings **14***a* can be removed with a dry etching method, such as an enhanced plasma etching method. Accordingly, the openings **14***a* in the polymer layer **14** are over multiple regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and expose them.

[0765] Next, referring to FIG. **28**D, an adhesion/barrier layer **16** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **14** and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **18** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **16** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **16** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum or tantalum nitride, and the material of the seed layer **18** may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0766] For example, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14** and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0767] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the polymer layer **14** and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-tungsten-alloy layer.

[0768] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14** and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08

and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0769] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14** and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0770] Referring to FIG. **28**E, after the step illustrated in FIG. **28**D, a photoresist layer **31** can be formed on the seed layer **18**, and multiple openings **31***a* in the photoresist layer **31** expose the seed layer **18**, which can be referred to as the step illustrated in FIG. **25**I. Next, multiple metal bumps or pillars **27** can be formed on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a*. The process of forming the metal bumps or pillars **27** on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a* as shown in FIG. **28**E can be referred to as the process of forming the metal bump or pillar **27** on the seed layer **18** of any previously described material exposed by the opening **31***a* and in the opening **31***a* as illustrated in FIG. **25**J. The specification of the metal bumps or pillars **27** shown in FIG. **28**E can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J.

[0771] Next, referring to FIG. **28**F, the photoresist layer **31** is removed, which can be referred to as the step illustrated in FIG. **25**K. Next, the seed layer **18** not under the metal bumps or pillars **27** is removed, and then the adhesion/barrier layer **16** not under the metal bumps or pillars **27** is removed, which can be referred to as the step illustrated in FIG. **25**L. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the interconnecting structures **88** provided by the metal layers **4** and **9**, the insulating layer **46**, the polymer layer **14**, the metal layers **16** and **18**, and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the interconnecting structures **88**. After the step illustrated in FIG. **28**F, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0772] Alternatively, after the step illustrated in FIG. **28**F, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0773] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **24**B, **24**C, **25**A-**25**F and **28**A-**28**F. After the steps illustrated in FIGS. **24**B, **24**C, **25**A-**25**F and **28**A-**28**F, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0774] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** provided by the metal layers **4** and **9** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**. The off-chip ESD circuit **43** is connected to the off-chip buffer **42** through the fine-line metal trace **639**.

[0775] FIG. **28**G is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a flux **32** can be formed in the openings **531**, **532**, **534**, **539** and **539'** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**. Next, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the insulating layer **46**, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **28**A-**28**F. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **28**F can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0776] After forming the structure shown in FIG. **28**G, the flux **32** is removed. Next, with the following steps being illustrated with reverse figures for simple explanation, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as ball-grid-array (BGA) substrate,

printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**, and/or to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0777] FIG. **28**H is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, the metal pads, bumps or traces **34***a* can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the process illustrated in FIG. **25**N. The specification of the metal pads, bumps or traces **34***a* shown in FIG. **28**H can be referred to as the specification of the metal pads, bumps or traces **34***a* as illustrated in FIG. **25**N. After forming the metal pads, bumps or traces **34***a*, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* , and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the insulating layer **46**, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate I, which can be referred to as the steps illustrated in FIGS. **28**A-**28**F. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **28**F can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'** can be performed after forming the metal bumps or pillars **27**.

[0778] After forming the structure shown in FIG. **28**H, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, through the metal pads, bumps or traces **34***a*, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0779] FIG. **28**I is a cross-sectional view showing a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**M. Next, multiple metal bumps **89** provided by the metal layers **89***a*, **89***b* and **89***c* can be formed on the polymer layer **98** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**, which can be referred to as the process illustrated in FIG. **15**M. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**. After forming the metal bumps **89**, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the insulating layer **46**, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **28**A-**28**F. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **28**F can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the steps of forming the patterned circuit layer **801**, the polymer layer **98**, the metal layer **89***a* and the metal bumps **89** can be performed after forming the metal bumps or pillars **27**.

[0780] After forming the structure shown in FIG. **28**I, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal sub-

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strate, glass substrate or ceramic substrate, through the metal bumps **89** of the over-passivation scheme **102**, and to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, through the metal bumps or pillars **27** of the bottom scheme **103**. The interconnecting structures **88** connect the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connect the metal bumps or pillars **27** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**. The patterned circuit layer **801** connects the off-chip buffer **42** to the internal circuits **21**, **22**, **23** and **24**, and connects the metal bumps **89** to the off-chip buffer **42**, to the off-chip ESD circuit **43** and to the internal circuits **21**, **22**, **23** and **24**.

[0781] FIG. **28**J is a cross-sectional view showing a package, which can be formed by a suitable process or processes, e.g., by the following steps. First, the semiconductor wafer **10** illustrated in FIG. **24**A includes multiple openings **531**, **532**, **534**, **539** and **539'** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**. The openings **531**, **532**, **534**, **539** and **539'** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **531**, **532**, **534**, **539** and **539'**. Next, a patterned circuit layer **801** composed of an adhesion/barrier/seed layer **8011** and a metal layer **8012** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'**, which can be referred to as the steps illustrated in FIGS. **15**D-**15**H. Next, a polymer layer **98** is formed on the metal layer **8012** of the patterned circuit layer **801** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points **801***a* of the metal layer **8012** of the patterned circuit layer **801** and expose them, which can be referred to as the process illustrated in FIG. **15**I. Accordingly, an over-passivation scheme **102** can be formed with the patterned circuit layer **801** and the polymer layer **98**, at the active side of the thinned silicon substrate **1**. Next, a flux can be formed in the openings **980** and on the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0782] After forming the flux, the step illustrated in FIG. **24**B can be performed. Next, the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* can be formed in the thinned silicon substrate **1**, and the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on the sidewalls of the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the interconnecting structures **88** can be formed in the through silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. Next, the insulating layer **46**, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18** and the metal bumps or pillars **27** can be formed at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **28**A-**28**F. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **28**F can be formed at the backside **1***a* of the thinned silicon substrate **1**. Next, the flux is removed to expose the contact points **801***a* of the metal layer **8012** exposed by the openings **980**.

[0783] After removing the flux, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, the semiconductor chip can be connected to a first external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by wirebonding multiple wires **129**, such as gold wires or copper wires, to the regions **801***a* of the metal layer **8012** of the over-passivation scheme **102** and to the first external circuit, and can be connected to a second external circuit, such as printed circuit board, ball-grid-array (BGA) substrate, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by bonding the metal bumps or pillars **27** of the bottom scheme **103** with the second external circuit. For example, the wirebonded wires **129** can be wirebonded gold wires ball bonded with the regions **801***a* of gold, copper, aluminum or palladium of the metal layer **8012** exposed by the openings **980**. Alternatively, the wirebonded wires **129** can be wirebonded copper wires ball bonded with the regions **801***a* of gold, copper, aluminum or palladium of the metal layer **8012** exposed by the openings **980**.

[0784] FIGS. **29**A-**29**T show simplified circuit diagrams of semiconductor chips where two dotted lines indicate a passivation layer **5** of the semiconductor chip and a backside **1***a* of a thinned silicon substrate **1** of the semiconductor chip, coarse traces indicate metal structures formed over the passivation layer **5** and formed under the backside **1***a*, and fine traces indicate metal traces between the passivation layer **5** and the silicon substrate **1**.

[0785] FIG. **29**A derives from FIG. **1**C. The semiconductor chip includes power interconnects **81** and **81**P, such as power buses, power traces or power lines, over the passivation layer **5**, a ground interconnect **82**, such as ground bus, ground trace or ground line, over the passivation layer **5**, a voltage regulator or converter circuit **41** between the passivation layer **5** and the backside **1***a* of the thinned silicon substrate **1**, multiple internal circuits **21**, **22**, **23** and **24** between the passivation layer **5** and the backside **1***a* of the thinned silicon substrate **1**, multiple fine-line metal traces **611**, **612***a*, **612***b*, **612***c*, **614**, **619**, **619'**, **621**, **622***a*, **622***b*, **622***c*, **624** and **629** between the passivation layer **5** and the backside **1***a* of the thinned silicon substrate **1**, multiple openings **511**, **512**, **514**, **519**, **519'** **521**, **522**, **524** and **529** in the passivation layer **5**, multiple through-silicon vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and **11***f* in the thinned silicon substrate **1**, multiple interconnecting structures **88** at the backside **1***a* of the thinned silicon substrate **1**, an inductor **36** at the backside **1***a* of the thinned silicon substrate **1**, and a capacitor **87** at the backside **1***a* of the thinned silicon substrate **1**. For improving the function of a regulator regulating the power voltage Vcc in the semiconductor chip, the inductor **36** and capacitor **87** can be provided to be incorporated into the voltage regulator or converter circuit **41**. The specification of the interconnecting structures **88** illustrated in FIG. **29**A can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structures **88** as shown in FIG. **29**A can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and **11***f* as shown in FIG. **29**A can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0786] The power interconnect **81**P can connect a power node of the voltage regulator or converter **41** to deliver a power voltage Vdd input from an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate. The power interconnect **81** can connect the node P of the voltage regulator or converter circuit **41** and the power nodes Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24** to distribute a regulated or converted power voltage Vcc. The ground interconnect **82** can connect the ground node Rs of the voltage regulator or converter circuit **41** and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** to distribute a ground reference voltage Vss.

[0787] The interconnecting structures **88** at the backside **1***a* of the thinned silicon substrate **1** include a ground interconnect **88***a*, such as ground bus, ground trace or ground line, used to deliver the ground reference voltage Vss, a power interconnect **88***b*, such as power bus, power trace or power line, used to deliver the power voltage Vdd input from the external circuit, and a power interconnect **88***c*, such as power bus, power trace or power line, used to deliver the regulated or converted power voltage Vcc output from the node P of the voltage regulator or converter circuit **41**.

[0788] The ground interconnect **88***a* can be connected to a terminal of the capacitor **87** formed under the backside **1***a* of the thinned silicon substrate **1**, to the ground node Rs of the voltage regulator or converter circuit **41** through the through-silicon via **11***b* and the fine-line metal trace **629**, to the ground interconnect **82** through the through-silicon vias **11***b*, **11***c*, **11***d* and **11***e* and the fine-line metal traces **629**, **621**, **622***a* and **624**, and to the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the through-silicon vias **11***c*, **11***d* and **11***e* and the fine-line metal traces **621**, **622***b*, **622***c* and **624**.

[0789] The power interconnect **88***b* can be connected to the power interconnect **81**P over the passivation layer **5** through the through-silicon via **11***a* and the fine-line metal trace **619**, to the power node of the voltage regulator or converter circuit **41** through the through-silicon via **11***a* and the fine-line metal trace **619**, and to a terminal of the inductor **36** formed under the backside **1***a* of the thinned silicon substrate **1**.

[0790] The power interconnect **88***c* can be connected to the power interconnect **81** through the through-silicon via **11***f* and the fine-line metal trace **619'**, to the node P of the voltage regulator or converter circuit **41** through the via **11***f* and the fine-line metal trace **619'**, to another terminal of the inductor **36**, and to another terminal of the capacitor **87**.

[0791] FIG. **29**B derives from FIGS. **29**A and **1**D. Addition to the structure of FIG. **29**A, the power interconnect **88***b* can be connected further to the node Dp of the ESD circuit **44** through the through-silicon via **11***h* and through the fine-line metal trace **649**, as shown in FIG. **29**B. The power interconnect **81**P can be connected further to the node Dp of the ESD circuit **44** through the opening **549** in the passivation layer **5** and through the fine-line metal trace **649**. The ground interconnect **88***a* can be connected further to the node Dg of the ESD circuit **44** through the through-silicon via **11***g* and through the fine-line metal trace **649'**. The ground interconnect **82** can be connected further to the node Dg of the ESD circuit **44** through the opening **549'** in the passivation layer **5** and through the fine-line metal trace **649'**. The process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e*, **11***f*, **11***g* and **11***h* as shown in FIG. **29**B can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0792] FIG. **29**C derives from FIG. **1**B. An interconnecting structure **88** can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The interconnecting structure **88** is a ground interconnect, such as ground bus, ground trace or ground line, used to deliver a ground voltage Vss and connected to the ground nodes Rs, Ts, Us, Vs and Ws through the through-silicon vias **11**. The specification of the interconnecting structure **88** illustrated in FIG. **29**C can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structure **88** as shown in FIG. **29**C can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**C can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0793] FIG. **29**D derives from FIG. **12**B. Interconnecting structures **88** can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. A capacitor **87** can be provided at the backside **1***a* of the thinned silicon substrate **1** using steps illustrated in FIGS. **32**A-**32**N, FIGS. **33**A-**33**K, FIGS. **33**N-**33**U, FIGS. **33**V and **33**W, FIG. **33**X and **33**Y, or FIGS. **35**A-**35**D. The interconnecting structures **88** includes a ground interconnect **88***a*, such as ground bus, ground trace or ground line, and a power interconnect **88***b*, such as power bus, power trace or power line. The ground interconnect **88***a* used to deliver a ground voltage Vss can be connected to a node of the ESD circuit **44**, to the ground nodes Ts, Us, Vs and Ws through the through-silicon vias **11**, and to a terminal of the capacitor **87**. The power interconnect **88***b* used to deliver a power voltage Vdd input from an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, another semiconductor chip, metal substrate, glass substrate or ceramic substrate, can be connected to the power interconnect **81**P over the passivation layer **5** and to the node Dp of the ESD circuit **44** through the through-silicon via **11** and the fine-line metal trace **649**. The power interconnect **88***b* also can be connected to another terminal of the capacitor **87**. The specification of the interconnecting structures **88** illustrated in FIG. **29**D can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structures **88** as shown in FIG. **29**D can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**D can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0794] Referring to FIG. **29**E, interconnecting structures **88** including a ground interconnect **88***a* and a power interconnect **88***b* can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **82**, shown in FIG. **12**C, over the passivation layer **5** can be replaced with the ground interconnect **88***a*, such as ground bus, ground trace or ground line, at the backside **1***a* of the thinned silicon substrate **1**, and the power bus **81**P, shown in FIG. **12**C, over the passivation layer **5** can be replaced with the power inter-

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connect **88***b*, such as power bus, power trace or power line, at the backside **1***a* of the thinned silicon substrate **1**. A capacitor **87** can be provided at the backside **1***a* of the thinned silicon substrate **1** using steps illustrated in FIGS. **32**A-**32**N, FIGS. **33**A-**33**K, FIGS. **33**N-**33**U, FIGS. **33**V and **33**W, FIG. **33**X and **33**Y, or FIGS. **35**A-**35**D. The ground interconnect **88***a* used to deliver a ground voltage Vss can be connected to the node Dg of the ESD circuit **44** and to the ground nodes Ts, Us, Vs and Ws through the through-silicon vias **11**. The ground interconnect **88***a* also can be connected to a terminal of the capacitor **87**. The power interconnect **88***b* used to deliver a power voltage Vdd input from an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, another semiconductor chip, metal substrate, glass substrate or ceramic substrate, can be connected to the node Dp of the ESD circuit **44** and to the power nodes Tp, Up, Vp and Wp through the through-silicon vias **11**. The power interconnect **88***b* also can be connected to another terminal of the capacitor **87**. The specification of the interconnecting structures **88** illustrated in FIG. **29**E can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structures **88** as shown in FIG. **29**E can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**E can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0795] Referring to FIG. **29**F, interconnecting structures **88** including a ground interconnect **88***a* and a power interconnect **88***b* can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **82**, shown in FIG. **12**D, over the passivation layer **5** can be replaced with the ground interconnect **88***a*, such as ground bus, ground trace or ground line, at the backside **1***a* of the thinned silicon substrate **1**, and the power metal trace, bus or plane **81**, shown in FIG. **12**D, over the passivation layer **5** can be replaced with the power interconnect **88***b*, such as power bus, power trace or power line, at the backside **1***a* of the thinned silicon substrate **1**. A capacitor **87** can be provided at the backside **1***a* of the thinned silicon substrate **1** using steps illustrated in FIGS. **32**A-**32**N, FIGS. **33**A-**33**K, FIGS. **33**N-**33**U, FIGS. **33**V and **33**W, FIG. **33**X and **33**Y, or FIGS. **35**A-**35**D. The ground interconnect **88***a* used to deliver a ground voltage Vss can be connected to the nodes Dg and Dg' of the ESD circuits **44** and **45** and to the ground nodes Ts, Us, Vs and Ws through the through-silicon vias **11**. The ground interconnect **88***a* also can be connected to a terminal of the capacitor **87**. The power interconnect **88***b* used to deliver a power voltage Vdd input from an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, another semiconductor chip, metal substrate, glass substrate or ceramic substrate, can be connected to the nodes Dp and Dp' of the ESD circuit **44** and **45** and to the power nodes Tp, Up, Vp and Wp through the through-silicon vias **11**. The power interconnect **88***b* also can be connected to another terminal of the capacitor **87**. The specification of the interconnecting structures **88** illustrated in FIG. **29**F can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structures **88** as shown in FIG. **29**F can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**F can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0796] Referring to FIG. **29**G, **29**H or **29**K, interconnecting structures **88** including two metal interconnects **88***c* and **88***d* can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **83**, shown in FIG. **8**B, **8**C or **8**F, over the passivation layer **5** can be replaced with the metal interconnect **88***c*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**, and the redistributed metal trace **83***r*, shown in FIG. **8**B, **8**C or **8**F, over the passivation layer **5** can be replaced with the metal interconnect **88***d*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate L The previously described metal bump or pillar **27** can be provided on the metal interconnect **88***d*. The previously described power interconnect **81**P, such as power bus, power trace or power line, connected to a node of the off-chip ESD circuit **43** through one opening **50** in the passivation layer **5** can be provided over the passivation layer **5** using the previously described top post-passivation technology. The previously described ground interconnect **82**, such as ground bus, ground trace or ground line, connected to another node of the off-chip ESD circuit **43** through another one opening **50** in the passivation layer **5** can be provided over the passivation layer **5** using the previously described top post-passivation technology. The specification of the interconnecting structures **88** illustrated in FIG. **29**G, **29**H or **29**K can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F, and the process of forming the interconnecting structures **88** as shown in FIG. **29**G, **29**H or **29**K can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**E The specification of the metal bump or pillar **27** illustrated in FIG. **29**G, **29**H or **29**K can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J, and the process of forming the metal bump or pillar **27** as shown in FIG. **29**G, **29**H or **29**K can be referred to as the process of forming the metal bump or pillar **27** as illustrated in FIGS. **25**G-**25**L. The process of forming the through-silicon vias **11** as shown in FIG. **29**O, **29**H or **29**K can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0797] Referring to FIG. **29**I, interconnecting structures **88** including two metal interconnects **88***c* and **88***d* can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **83**, shown in FIG. **8**D, over the passivation layer **5** can be replaced with the metal interconnect **88***c*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**, and the redistributed metal trace **83***r*, shown in FIG. **8**D, over the passivation layer **5** can be replaced with the metal interconnect **88***d*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**. The previously described metal bump or pillar **27** can be provided on the metal interconnect **88***d*. The previously described power interconnect **81**P, such as power bus, power trace or power line, connected to two nodes of the two off-chip ESD circuits **43** through two openings **50** in the passivation layer **5** can be provided over the passivation layer **5** using the previously described top post-passivation technology. The previously described ground interconnect **82**,

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such as ground bus, ground trace or ground line, connected to another two nodes of the two off-chip ESD circuits **43** through another two openings **50** in the passivation layer **5** can be provided over the passivation layer **5** using the previously described top post-passivation technology. The specification of the interconnecting structures **88** illustrated in FIG. **29**I can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F, and the process of forming the interconnecting structures **88** as shown in FIG. **29**I can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The specification of the metal bump or pillar **27** illustrated in FIG. **29**I can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J, and the process of forming the metal bump or pillar **27** as shown in FIG. **29**I can be referred to as the process of forming the metal bump or pillar **27** as illustrated in FIGS. **25**G-**25**L. The process of forming the through-silicon vias **11** as shown in FIG. **29**I can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0798] Referring to FIG. **29**J, interconnecting structures **88** including three metal interconnects **88***c*, **88***d* and **88***e* can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **83**, shown in FIG. **8**E, over the passivation layer **5** can be replaced with the metal interconnect **88***c*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**, the redistributed metal trace **83***r*, shown in FIG. **8**E, over the passivation layer **5** can be replaced with the metal interconnect **88***d*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**, and the metal trace, bus or plane **83***s*, shown in FIG. **8**E, over the passivation layer **5** can be replaced with the metal interconnect **88***e*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**. The previously described metal bump or pillar **27** can be provided on the metal interconnect **88***d*. The previously described power interconnect **81**P, such as power bus, power trace or power line, connected to a node of the off-chip ESD circuit **43** through one opening **50** in the passivation layer **5** can be provided over the passivation layer **5** using the previously described top post-passivation technology. The previously described ground interconnect **82**, such as ground bus, ground trace or ground line, connected to another node of the off-chip ESD circuit **43** through another one opening **50** in the passivation layer **5** can be provided over the passivation layer **5** using the previously described top post-passivation technology. The specification of the interconnecting structures **88** illustrated in FIG. **29**J can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F, and the process of forming the interconnecting structures **88** as shown in FIG. **29**J can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The specification of the metal bump or pillar **27** illustrated in FIG. **29**J can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J, and the process of forming the metal bump or pillar **27** as shown in FIG. **29**J can be referred to as the process of forming the metal bump or pillar **27** as illustrated in FIGS. **25**G-**25**L. The process of forming the through-silicon vias **11** as shown in FIG. **29**J can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0799] Referring to FIG. **29**L or **29**M, an interconnecting structure **88** can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **83**, shown in FIG. **5**B or **5**S, over the passivation layer **5** can be replaced with the interconnecting structure **88** at the backside **1***a* of the thinned silicon substrate I. The interconnecting structure **88**, such as metal interconnect, metal trace or metal line, can be connected to the metal interconnects **631**, **632** and **634**, such as metal buses or metal traces, through the through-silicon vias **11**. The specification of the interconnecting structure **88** illustrated in FIG. **29**L or **29**M can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structure **88** as shown in FIG. **29**L or **29**M can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**L or **29**M can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0800] Referring to FIG. **29**N, an interconnecting structure **88** can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **83'**, shown in FIG. **5**K, over the passivation layer **5** can be replaced with the interconnecting structure **88** at the backside **1***a* of the thinned silicon substrate **1**. The interconnecting structure **88**, such as metal interconnect, metal trace or metal line, can be connected to the metal interconnects **631'**, **632'** and **634'**, such as metal buses or metal traces, through the through-silicon vias **11**. The specification of the interconnecting structure **88** illustrated in FIG. **29**N can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structure **88** as shown in FIG. **29**N can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**N can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0801] Referring to FIG. **29**O, **29**P, **29**Q, **29**R, **29**S or **29**T, interconnecting structures **88** including two metal interconnects **88***f* and **88***g* can be provided at the backside **1***a* of the thinned silicon substrate **1** and in through-silicon vias **11** in the thinned silicon substrate **1**. The metal trace, bus or plane **83**, shown in FIG. **5**U, **5**V, **5**W, **5**X, **5**Y or **5**Z, over the passivation layer **5** can be replaced with the metal interconnect **88***f*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**, and the address bus **85**, shown in FIG. **5**U, **5**V, **5**W, **5**X, **5**Y or **5**Z, over the passivation layer **5** can be replaced with the metal interconnect **88***g*, such as metal trace or metal line, at the backside **1***a* of the thinned silicon substrate **1**. The specification of the interconnecting structures **88** illustrated in FIG. **29**O, **29**P, **29**Q, **29**R, **29**S or **29**T can be referred to as the specification of the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the interconnecting structures **88** as shown in FIG. **29**O, **29**P, **29**Q, **29**R, **29**S or **29**T can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The process of forming the through-silicon vias **11** as shown in FIG. **29**O, **29**P, **29**Q, **29**R, **29**S or **29**T can be referred to as the process of forming the

through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N.

[0802] In the following, a process illustrated in FIGS. **30**A-**30**F is introduced for forming the inductor **36** and the ground trace **88***a* as illustrated in FIGS. **29**A and **29**B. FIG. **30**A is a cross-sectional view showing the silicon substrate **1** and other elements as described above in the semiconductor wafer **10**, and the silicon substrate **1** has a thickness t**1** between 600 and 1000 micrometers, between 50 micrometers and 1 millimeter or between 75 and 250 micrometers. Alternatively, the silicon substrate **1** can be replaced by other semiconductor substrate, such as silicon-germanium (SiGe) substrate or gallium arsenide (GaAs) substrate.

[0803] Referring to FIG. **30**B, the silicon substrate **1** of the semiconductor wafer **10** illustrated FIG. **30**A is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, multiple through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing multiple regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. The through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. The process of forming the through-silicon via **11***f* in the thinned silicon substrate **1** and in the dielectric layer **30** and forming the insulating layer **3** on the sidewall of the through-silicon via **11***f* as shown in FIG. **30**B can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* in the thinned silicon substrate **1** and in the dielectric layer(s) **30** and forming the insulating layer **3** on the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the metal layer **4** composed of the adhesion/barrier layer **4***a* and the seed layer **4***b* can be formed in the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* and on the insulating layer **3**, which can be referred to as the step illustrated in FIG. **25**A.

[0804] After forming the seed layer **4***b* of the metal layer **4**, a photoresist layer **29**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, can be formed on the seed layer **4***b* of the metal layer **4** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **29** is patterned with the processes of exposure and development to form an opening **29***a* and a coil-shaped opening **29***b* in the photoresist layer **29** exposing the seed layer **4***b* of the metal layer **4**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **29** during the process of exposure. The process of forming the photoresist layer **29** on the seed layer **4***b*, forming the opening **29***a* in the photoresist layer **29** and forming the coil-shaped opening **29***b* in the photoresist layer **29** as shown in FIG. **30**B can be referred to as the process of forming the photoresist layer **29** on the seed layer **4***b* and forming the openings **29***a* in the photoresist layer **29** as illustrated in FIGS. **25**B-**25**C.

[0805] Next, referring to FIG. **30**C, a bulk metal layer **9** can be formed in the openings **29***a* and **29***b* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* and **29***b* by a process including an electroplating process. The process of forming the bulk metal layer **9** in the openings **29***a* and **29***b* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* and **29***b* as shown in FIG. **30**C can be referred to as the process of forming the bulk metal layer **9** in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* as illustrated in FIG. **25**D. The specification of the bulk metal layer **9** shown in FIG. **30**C can be referred to as the specification of the bulk metal layer **9** as illustrated in FIG. **25**D.

[0806] Referring to FIG. **30**D, after the step illustrated in FIG. **30**C, the photoresist layer **29** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **29** could remain on the bulk metal layer **9** and on the seed layer **4***b* of the metal layer **4**. Thereafter, the residuals can be removed from the bulk metal layer **9** and from the seed layer **4***b* of the metal layer **4** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0807] Referring to FIG. **30**E, after the step illustrated in FIG. **30**D, the metal layer **4** not under the bulk metal layer **9** is removed by etching the seed layer **4***b* not under the bulk metal layer **9**, and then etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**. The process of removing the seed layer **4***b* not under the bulk metal layer **9** and removing the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as shown in FIG. **30**E can be referred to as the process of removing the seed layer **4***b* not under the bulk metal layer **9** and removing the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as illustrated in FIG. **25**F.

[0808] Accordingly, the coil **36** and the metal interconnect **88***a* are formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**. The coil **36** provided by the metal layers **4** and **9** at the backside **1***a* of the thinned silicon substrate **1** has a first contact point **36***a* connected to the node P of the voltage regulator or converter circuit **41** through the bulk metal layer **9** in the through-silicon via **11***f* and through the fine-line metal structure **619'**, and a second contact point **36***b* connected to the power node of the voltage regulator or converter circuit **41** through the bulk metal layer **9** in the through-silicon via **11** a and through the fine-line metal structure **619**. FIG. **30**F shows a top view of the coil **36**. The coil **36** can be used for an inductor. The metal interconnect **88***a* can be provided by the metal layers **4** and **9** at the backside **1***a* of the thinned silicon substrate **1**, and can connect the internal circuits **22** and **23** to the internal circuit **24**. The internal circuits **22** and **23** can be connected to the internal circuit **24** through the metal interconnect **88***a* and the fine-line metal traces **622** and **624**.

[0809] After the, step illustrated in FIG. **30**E, using a die-sawing process, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, there is no metal bump or wirebonded wire formed on the bulk metal layer **9** of the semiconductor chip for connecting the coil **36** or the metal interconnect **88***a* to an external circuit.

[0810] Alternatively, in the chip package, there is a wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on the bulk metal layer **9** of the semiconductor chip for connecting the coil **36** to a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or

ceramic substrate, and there is another wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on a region of the metal interconnect **88***a* of the semiconductor chip for connecting the metal interconnect **88***a* to the first external circuit or to a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate.

[0811] Alternatively, in the chip package, there is a first wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on the bulk metal layer **9** of the semiconductor chip for connecting the contact point **36***b* of the coil **36** to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and there is a second wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on the bulk metal layer **9** of the semiconductor chip for connecting the contact point **36***a* of the coil **36** to the first external circuit or a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to output a regulated or converted power voltage Vcc to the first external circuit or the second external circuit. There is a third wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on the bulk metal layer **9** of the semiconductor chip for connecting the metal interconnect **88***a* to a ground bus or plane of the first external circuit or the second external circuit.

[0812] Alternatively, in the chip package, there is a first metal bump, such as gold bump, copper bump, nickel bump or solder bump, on the bulk metal layer **9** of the semiconductor chip for connecting the contact point **36***b* of the coil **36** to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and there is a second metal bump, such as gold bump, copper bump, nickel bump or solder bump, on the bulk metal layer **9** of the semiconductor chip for connecting the contact point **36***a* of the coil **36** to the first external circuit or a second external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to output a regulated or converted power voltage Vcc to the first external circuit or the second external circuit. There is a third metal bump, such as gold bump, copper bump, nickel bump or solder bump, on the bulk metal layer **9** of the semiconductor chip for connecting the metal interconnect **88***a* to a ground bus or plane of the first external circuit or the second external circuit.

[0813] In the following, FIGS. **30**G, **30**H and **30**I show a process for forming multiple metal bumps or pillars **27** over the bulk metallayer **9** of the semiconductor wafer **10** for being used to connect the coil **36** to the first external circuit and/or the second external circuit and connect the metal interconnect **88***a* to the first external circuit or the second external circuit.

[0814] Referring to FIG. **30**G, after the step illustrated in FIG. **30**E, a polymer layer **14** can be formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, and multiple openings **14***a* in the polymer layer **14** are over multiple regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and expose them, which can be referred to as the step illustrated in FIG. **25**G. The polymer layer **14** has a thickness larger than 2 micrometers, such as between 3 and 50 micrometers, and preferably between 5 and 25 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0815] Next, referring to FIG. **30**H, the adhesion/barrier layer **16** can be formed on the polymer layer **14** and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, and then the seed layer **18** can be formed on the adhesion/barrier layer **16**, which can be referred to as the step illustrated in FIG. **25**H. Next, the photoresist layer **31** can be formed on the seed layer **18**, and multiple openings **31***a* in the photoresist layer **31** expose the seed layer **18**, which can be referred to as the step illustrated in FIG. **25**I. Next, the metal bumps or pillars **27** can be formed on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31** a. The process of forming the metal bumps or pillars **27** on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a* as shown in FIG. **30**H can be referred to as the process of forming the metal bump or pillar **27** on the seed layer **18** of any previously described material exposed by the opening **31***a* and in the opening **31***a* as illustrated in FIG. **25**J. The specification of the metal bumps or pillars **27** shown in FIG. **30**H can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J.

[0816] Next, referring to FIG. **30**I, the photoresist layer **31** can be removed, which can be referred to as the step illustrated in FIG. **25**K. Next, the seed layer **18** not under the metal bumps or pillars **27** can be removed, and then the adhesion/barrier layer **16** not under the metal bumps or pillars **27** can be removed, which can be referred to as the step illustrated in FIG. **25**L. Accordingly, the metal bumps or pillars **27** are formed over the bulk metal layer **9** and connect with the bulk metal layer **9**, and a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the coil **36**, the metal interconnect **88***a*, the metal layers **16** and **18**, the metal bumps or pillars **27**, and the polymer layer **14**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**.

[0817] After forming the structure shown in FIG. **30**I, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. Alternatively, after forming the structure shown in FIG. **30**I, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **30**B-**30**E and **30**G-**30**I, after the steps illustrated in FIGS. **30**B-**30**E and **30**G-**30**I, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0818] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, a first metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***b* of the coil **36** to the power bus or plane of the first external circuit to receive the external power voltage Vdd from the first external circuit. A second metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to the first external circuit or the second external circuit to output the regulated or converted power voltage Vcc to the first external circuit or the second external circuit. A third metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to the ground bus or plane of the first external circuit or the second external circuit.

[0819] FIGS. **30**J, **30**K and **30**L show a process for forming a semiconductor wafer according to the present disclosure. Referring to FIG. **30**J, the semiconductor wafer **10** illustrated in FIG. **30**A includes multiple openings **519**, **519'**, **521**, **522** and **524** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**, and a flux **32** can be formed in the openings **519**, **519'**, **521**, **522** and **524** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524**. The openings **519**, **519'**, **521**, **522** and **524** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **519**, **519'**, **521**, **522** and **524**.

[0820] Referring to FIG. **30**K, after forming the flux **32**, the silicon substrate **1** is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the coil **36**, the metal interconnect **88***a*, the polymer layer **14** and the metal bumps or pillars **27** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **30**B-**30**E and **30**G-**30**I. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **30**I can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0821] Referring to FIG. **30**L, after forming the structure shown in FIG. **30**K, the flux **32** is removed. Next, using the steps illustrated in FIGS. **15**D-**15**H, multiple patterned circuit layers **812** composed of an adhesion/barrier/seed layer **8121** and a metal layer **8122** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519** and **519'**, and a patterned circuit layer **821** composed of an adhesion/barrier/seed layer **8211** and a metal layer **8212** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**. Next, a polymer layer **98** is formed on the metal layer **8122** of the patterned circuit layers **812**, on the metal layer **8212** of the patterned circuit layer **821** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points of the metal layers **8122** and **8212** and expose them, which can be referred to as the step illustrated in FIG. **15**I. Next, multiple metal bumps **89** provided by triple metal layers **89***a*, **89***b* and **89***c* are formed on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. Accordingly, an over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**. Alternatively, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**.

[0822] For example, the metal layer **89***a* can be an adhesion/barrier layer that can be a titanium-containing layer, such as titanium layer, titanium-tungsten-alloy layer or titanium-nitride layer, a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, or a chromium-containing layer, such as chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. The metal layer **89***b* can be a copper seed layer having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **89***a*. The metal layer **89***c* can be an electroplated copper layer having a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the copper seed layer **89***b* and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. Sidewalls of the electroplated copper layer **89***c* are not covered by the adhesion/barrier layer **89***a* and the copper seed layer **89***b*.

[0823] Alternatively, the metal layer **89***a* can be an adhesion/barrier layer that can be a titanium-containing layer, such as titanium layer, titanium-tungsten-alloy layer or titanium-nitride layer, a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, or a chromium-containing layer, such as chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. The metal layer **89***b* can be a gold seed layer having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **89***a*. The metal layer **89***c* can be an electroplated gold layer having a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the gold seed layer **89***b* and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. Sidewalls of the electroplated gold layer **89***c* are not covered by the adhesion/barrier layer **89***a* and the gold seed layer **89***b*.

[0824] Alternatively, the metal layer **89***a* can be an adhesion/barrier layer that can be a titanium-containing layer, such as titanium layer, titanium-tungsten-alloy layer or titanium-nitride layer, a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, or a chromium-containing layer, such as chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the

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polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. The metal layer **89***b* can be a copper seed layer having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **89***a*. The metal layer **89***c* can be an electroplated nickel layer having a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the copper seed layer **89***b* and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. Sidewalls of the electroplated nickel layer **89***c* are not covered by the adhesion/barrier layer **89***a* and the copper seed layer **89***b*.

[0825] Alternatively, the metal layer **89***a* can be an adhesion/barrier layer that can be a titanium-containing layer, such as titanium layer, titanium-tungsten-alloy layer or titanium-nitride layer, a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, or a chromium-containing layer, such as chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. The metal layer **89***b* can be a copper seed layer having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **89***a*. The metal layer **89***c* can be triple metal layers including an electroplated copper layer having a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the copper seed layer **89***b* and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, an electroplated or electroless plated nickel layer having a thickness larger than 1 micrometer, such as between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, and an electroplated or electroless plated gold layer having a thickness between 0.005 and 1 micrometers, and preferably between 0.05 and 0.1 micrometers, on the electroplated or electroless plated nickel layer and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. Sidewalls of the metal layer **89***c* are not covered by the adhesion/barrier layer **89***a* and the copper seed layer **89***b*.

[0826] Alternatively, the metal layer **89***a* can be an adhesion/barrier layer that can be a titanium-containing layer, such as titanium layer, titanium-tungsten-alloy layer or titanium-nitride layer, a tantalum-containing layer, such as tantalum layer or tantalum-nitride layer, or a chromium-containing layer, such as chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. The metal layer **89***b* can be a copper seed layer having a thickness smaller than 1 micrometer, such as between 0.005 and 0.9 micrometers, and preferably between 0.05 and 0.5 micrometers, on the adhesion/barrier layer **89***a*. The metal layer **89***c* can be triple metal layers including an electroplated copper layer having a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the copper seed layer **89***b* and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, an electroplated or electroless plated nickel layer having a thickness larger than 1 micrometer, such as between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, on the electroplated copper layer and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, and a solder bump that can be a bismuth-containing bump, an indium-containing bump or a tin-containing bump of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, having a thickness larger than 5 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, on the electroplated or electroless plated nickel layer and over the contact points of the metal layers **8122** and **8212** exposed by the openings **980**. Sidewalls of the metal layer **89***c* are not covered by the adhesion/barrier layer **89***a* and the copper seed layer **89***b*.

[0827] After forming the structure shown in FIG. **30**L, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0828] In the chip package, for example, a first metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***b* of the coil **36** to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. A third metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the first external circuit. A first metal bump **89** connected the metal trace, bus or plane **81** of the semiconductor chip may be connected to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal bumps **89** connected to the ground plane, bus or trace **82** of the semiconductor chip may be connected to a ground bus or plane of the second external circuit.

[0829] Alternatively, in the chip package, a first metal bump **89** connected to the metal trace, bus or plane **81**P of the semiconductor chip may be connected to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump **89** connected the metal trace, bus or plane **81** of the semiconductor chip may be connected to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal bumps **89** connected to the ground plane, bus or trace **82** of the semiconductor chip may be connected to a ground bus or plane of the first external circuit. A first metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power

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voltage Vcc to the second external circuit. A second metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the second external circuit.

[0830] FIGS. **30**M and **30**N show a process for forming a semiconductor wafer according to the present disclosure. Referring to FIG. **30**M, the semiconductor wafer **10** illustrated in FIG. **30**A includes multiple openings **519**, **519'**, **521**, **522** and **524** in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600**, and multiple metal pads, bumps or traces **34***a* provided by two metal layers **32** and **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524**, which can be referred to as the steps illustrated in FIG. **25**N. The openings **519**, **519'**, **521**, **522** and **524** are over the regions **600***a* of the metal traces or pads **600**, and the regions **600***a* of the metal traces or pads **600** are at bottoms of the openings **519**, **519'**, **521**, **522** and **524**.

[0831] Referring to FIG. **30**N, after forming the metal pads, bumps or traces **34***a*, the silicon substrate **1** is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the coil **36**, the metal interconnect **88***a*, the polymer layer **14** and the metal bumps or pillars **27** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **30**B-**30**E and **30**G-**30**I. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **30**I can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** can be performed after forming the metal bumps or pillars **27**.

[0832] After forming the structure shown in FIG. **30**N, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0833] In the chip package, for example, a first metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***b* of the coil **36** to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. A third metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the first external circuit. A first metal pad, bump or trace **34***a* connected the fine-line metal trace **619'** of the semiconductor chip may be connected to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal pads, bumps or traces **34***a* connected to the fine-line metal traces **621**, **622** and **624** of the semiconductor chip may be connected to a ground bus or plane of the second external circuit.

[0834] Alternatively, in the chip package, a first metal pad, bump or trace **34***a* connected to the fine-line metal trace **619** of the semiconductor chip may be connected to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal pad, bump or trace **34***a* connected to the fine-line metal trace **619'** of the semiconductor chip may be connected to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal pads, bumps or traces **34***a* connected to the fine-line metal traces **621**, **622** and **624** of the semiconductor chip may be connected to a ground bus or plane of the first external circuit. A first metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. A second metal bump or pillar **27** connected to the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the second external circuit.

[0835] In the following, FIGS. **31**A-**31**F show a process for forming multiple metal bumps or pillars **27** on the bulk metal layer **9** of the semiconductor wafer **10** for being used to connect the coil **36** to the first external circuit and/or the second external circuit and connect the metal interconnect **88***a* to the first external circuit or the second external circuit.

[0836] Referring to FIG. **31**A, after the steps illustrated in FIGS. **30**B and **30**C, a photoresist layer **51**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 200 micrometers, and preferably between 2 and 150 micrometers, can be formed on the photoresist layer **29** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **51** is patterned with the processes of exposure and development to form multiple openings **51***a* in the photoresist layer **51** exposing multiple regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **51** during the process of exposure. Each of the three openings **51***a* has a width W**3** larger than 5 micrometers, such as between 10 and 30 micrometers, between 20 and 50 micrometers or between 50 and 150 micrometers. The process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as shown in FIG. **31**A can be

referred to as the process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as illustrated in FIG. **26**A.

[0837] Referring to FIG. **31**B, after the step illustrated in FIG. **31**A, the metal bumps or pillars **27** having a thickness larger than 1 micrometer are formed in the openings **51***a* and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a*. The material of the three metal bumps or pillars **27** may include gold, nickel, tin, solder, palladium, copper, aluminum or a composite of the previously described materials. The process of forming the metal bumps or pillars **27** in the openings **51***a* and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* as shown in FIG. **31** B can be referred to as the process of forming the metal bumps or pillars **27** in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* as illustrated in FIG. **26**B. The specification of the metal bumps or pillars **27** shown in FIG. **31**B can be referred to as the specification of the metal bumps or pillars **27** as illustrated in FIG. **26**B.

[0838] Referring to FIG. **31**C, after forming the metal bumps or pillars **27**, the photoresist layers **29** and **51** are removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layers **29** and **51** could remain on the seed layer **4***b* of the metal layer **4**, on the bulk metal layer **9** and on the metal bumps or pillars **27**. Thereafter, the residuals can be removed from the seed layer **4***b* of the metal layer **4**, from the bulk metal layer **9** and from the metal bumps or pillars **27** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0839] Accordingly, the metal bumps or pillars **27** are formed on the bulk metal layer **9** and contact with the bulk metal layer **9** after removing the photoresist layers **29** and **51**. Each of the metal bumps or pillars **27** has a width W**3** larger than 5 micrometers, such as between 10 and 30 micrometers, between 20 and 50 micrometers or between 50 and 150 micrometers, and larger than that of each of the fine-line metal layers **60**, and has a height H**1** larger than 1 micrometer, such as between 1 and 300 micrometers, between 5 and 250 micrometers, between 10 and 100 micrometers or between 5 and 50 micrometers.

[0840] Alternatively, another process for forming the metal bumps or pillars **27** on the bulk metal layer **9** can be performed by the following steps. Referring to FIG. **31**D, after the steps illustrated in FIGS. **30**B-**30**D, the photoresist layer **51** illustrated in FIG. **31**A can be formed on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and on the seed layer **4***b* of the metal layer **4** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **51** is patterned with the processes of exposure and development to form the openings **51***a* in the photoresist layer **51** exposing the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**. Each of the openings **51***a* has a width W**3** larger than 5 micrometers, such as between 10 and 30 micrometers, between 20 and 50 micrometers or between 50 and 150 micrometers. The process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as shown in FIG. **31**D can be referred to as the process of forming the photoresist layer **51** and the openings **51***a* in the photoresist layer **51** as illustrated in FIG. **26**A.

[0841] Referring to FIG. **31**E, after the step illustrated in FIG. **31**D, the metal bumps or pillars **27** having a thickness larger than 1 micrometer are formed in the openings **51***a* and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a*. The material of the metal bumps or pillars **27** may include gold, nickel, tin, solder, palladium, copper, aluminum or a composite of the previously described materials. The process of forming the metal bumps or pillars **27** in the openings **51***a* and on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* as shown in FIG. **31** E can be referred to as the process of forming the metal bumps or pillars **27** in the openings **51***a* and on the regions **9***a* of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **51***a* as illustrated in FIG. **26**B. The specification of the metal bumps or pillars **27** shown in FIG. **31**E can be referred to as the specification of the metal bumps or pillars **27** as illustrated in FIG. **26**B.

[0842] After forming the metal bumps or pillars **27** as illustrated in FIG. **31**E, the photoresist layer **51** is removed using an inorganic solution or using an organic solution with amide. Accordingly, the metal bumps or pillars **27** can be formed on the bulk metal layer **9** after removing the photoresist layer **51**.

[0843] Referring to FIG. **31**F, after removing the photoresist layers **29** and **51**, the metal layer **4** not under the bulk metal layer **9** is removed by etching the seed layer **4***b* not under the bulk metal layer **9**, and then etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**. The process of removing the seed layer **4***b* not under the bulk metal layer **9** and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as shown in FIG. **31**F can be referred to as the process of removing the seed layer **4***b* not under the bulk metal layer **9** and the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as illustrated in FIG. **25**F.

[0844] Accordingly, the coil **36** and the metal interconnect **88***a* are formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the three metal bumps or pillars **27** are directly formed on the bulk metal layer **9**. The specification of the coil **36** and the metal interconnect **88***a* shown in FIG. **31**F can be referred to as the specification of the coil **36** and the metal interconnect **88***a* as illustrated in FIG. **30**E, respectively. FIG. **30**F shows a top view of the coil **36** shown in FIG. **31**F. The metal bumps or pillars **27** on the bulk metal layer **9** can be used to connect the coil **36** to the first external circuit and/or the second external circuit and connect the metal interconnect **88***a* to the first external circuit or the second external circuit.

[0845] Referring to FIG. **31**G, after the step illustrated in FIG. **31**F, a polymer layer **14** is formed on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9**, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and multiple openings **14***a* are formed in the polymer layer **14** to uncover top surfaces and sidewalls of the metal bumps or pillars **27**. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the coil **36**, the metal interconnect **88***a*, the

polymer layer **14** and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**. After the step illustrated in FIG. **31**G, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0846] Alternatively, after the step illustrated in FIG. **31**G, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0847] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **30**B, **30**C and **31**A-**31**G. After the steps illustrated in FIGS. **30**B, **30**C and **31**A-**31**G, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0848] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, a first metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***b* of the coil **36** to the power bus or plane of the first external circuit to receive the external power voltage Vdd from the first external circuit. A second metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to the first external circuit or the second external circuit to output the regulated or converted power voltage Vcc to the first external circuit or the second external circuit. A third metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to the ground bus or plane of the first external circuit or the second external circuit.

[0849] FIGS. **31**H and **31**I are cross sectional views showing a process for forming a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. Referring to FIG. **31**H, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**J is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the coil **36**, the metal interconnect **88***a*, the polymer layer **14** and the metal bumps or pillars **27** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **30**B, **30**C and **31**A-**31**G. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **31**G can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0850] Referring to FIG. **31**I, after forming the structure shown in FIG. **31**H, the flux **32** is removed. Next, using the steps illustrated in FIGS. **15**D-**15**H, multiple patterned circuit layers **812** composed of an adhesion/barrier/seed layer **8121** and a metal layer **8122** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519** and **519'**, and a patterned circuit layer **821** composed of an adhesion/barrier/seed layer **8211** and a metal layer **8212** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**. Next, a polymer layer **98** is formed on the metal layer **8122** of the patterned circuit layers **812**, on the metal layer **8212** of the patterned circuit layer **821** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points of the metal layers **8122** and **8212** and expose them, which can be referred to as the step illustrated in FIG. **15**I. Next, multiple metal bumps **89** provided by triple metal layers **89***a*, **89***b* and **89***c* are formed on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, which can be referred to as the step illustrated in FIG. **30**L. The specification of the metal bumps **89** shown in FIG. **31**I can be referred to as the specification of the metal bumps **89** as illustrated in FIG. **30**L. Accordingly, an over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**. Alternatively, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**.

[0851] After forming the structure shown in FIG. **31**I, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0852] In the chip package, for example, a first metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***b* of the coil **36** to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. A third metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the first external circuit. A first metal bump **89** connected the metal trace, bus or plane **81** of the semiconductor chip may be connected to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal bumps **89** connected to the ground plane, bus or trace **82** of the semiconductor chip may be connected to a ground bus or plane of the second external circuit.

[0853] Alternatively, in the chip package, a first metal bump **89** connected to the metal trace, bus or plane **81**P of the semiconductor chip may be connected to a first external circuit, such as semiconductor chip, printed circuit board, ball-

grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump **89** connected the metal trace, bus or plane **81** of the semiconductor chip may be connected to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal bumps **89** connected to the ground plane, bus or trace **82** of the semiconductor chip may be connected to a ground bus or plane of the first external circuit. A first metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. A second metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the second external circuit.

[0854] FIG. **31**J is a cross sectional view showing a process for forming a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**M is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the coil **36**, the metal interconnect **88***a*, the polymer layer **14** and the metal bumps or pillars **27** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **30**B, **30**C and **31**A-**31**G. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **31**G can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** can be performed after forming the polymer layer **14**.

[0855] After forming the structure shown in FIG. **31**J, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0856] In the chip package, for example, a first metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***b* of the coil **36** to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. A third metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the first external circuit. A first metal pad, bump or trace **34***a* connected the fine-line metal trace **619'** of the semiconductor chip may be connected to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal pads, bumps or traces **34***a* connected to the fine-line metal traces **621**, **622** and **624** of the semiconductor chip may be connected to a ground bus or plane of the second external circuit.

[0857] Alternatively, in the chip package, a first metal pad, bump or trace **34***a* connected to the fine-line metal trace **619** of the semiconductor chip may be connected to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal pad, bump or trace **34***a* connected to the fine-line metal trace **619'** of the semiconductor chip may be connected to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal pads, bumps or traces **34***a* connected to the fine-line metal traces **621**, **622** and **624** of the semiconductor chip may be connected to a ground bus or plane of the first external circuit. A first metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the contact point **36***a* of the coil **36** to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. A second metal bump or pillar **27** on the bulk metal layer **9** of the semiconductor chip may connect the metal interconnect **88***a* to a ground bus or plane of the second external circuit.

[0858] In the following, a process illustrated in FIGS. **32**A-**32**N is introduced for forming the capacitor **87** in FIGS. **29**A, **29**B and **29**D. Referring to FIG. **32**A, the silicon substrate **1** of the semiconductor wafer **10** illustrated FIG. **30**A is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate I. Next, multiple through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing multiple regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. The through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. The process of forming the through-silicon via **11***f* in the thinned silicon substrate **1** and in the dielectric layer **30** and forming the insulating layer **3** on the sidewall of the through-silicon via **11***f* as shown in FIG. **32**A can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* in the thinned silicon substrate **1** and in the dielectric layer(s) **30** and forming the insulating layer **3** on the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the metal layer **4** composed of the

adhesion/barrier layer **4***a* and the seed layer **4***b* can be formed in the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* and on the insulating layer **3**, which can be referred to as the step illustrated in FIG. **25**A.

[0859] After forming the seed layer **4***b* of the metal layer **4**, a photoresist layer **29**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1.5 micrometers, such as between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, can be formed on the seed layer **4***b* of the metal layer **4** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **29** is patterned with the processes of exposure and development to form multiple openings **29***a* in the photoresist layer **29** exposing the seed layer **4***b* of the metal layer **4**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **29** during the process of exposure. The process of forming the photoresist layer **29** on the seed layer **4***b* and forming the openings **29***a* in the photoresist layer **29** as shown in FIG. **32**A can be referred to as the process of forming the photoresist layer **29** on the seed layer **4***b* and forming the openings **29***a* in the photoresist layer **29** as illustrated in FIGS. **25**B-**25**C.

[0860] Next, referring to FIG. **32**B, a bulk metal layer **9** can be formed in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* by a process including an electroplating process. The process of forming the bulk metal layer **9** in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* as shown in FIG. **32**B can be referred to as the process of forming the bulk metal layer **9** in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* as illustrated in FIG. **25**D. The specification of the bulk metal layer **9** shown in FIG. **32**B can be referred to as the specification of the bulk metal layer **9** as illustrated in FIG. **25**D.

[0861] Referring to FIG. **32**C, after the step illustrated in FIG. **32**B, the photoresist layer **29** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **29** could remain on the bulk metal layer **9** and on the seed layer **4***b* of the metal layer **4**. Thereafter, the residuals can be removed from the bulk metal layer **9** and from the seed layer **4***b* of the metal layer **4** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0862] Referring to FIG. **32**D, after the step illustrated in FIG. **32**C, the metal layer **4** not under the bulk metal layer **9** is removed by etching the seed layer **4***b* not under the bulk metal layer **9**, and then etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**. The process of removing the seed layer **4***b* not under the bulk metal layer **9** and removing the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as shown in FIG. **32**D can be referred to as the process of removing the seed layer **4***b* not under the bulk metal layer **9** and removing the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as illustrated in FIG. **25**F.

[0863] Next, referring to FIG. **32**E, a dielectric layer **85** is formed on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and on the insulating layer **3** not under the metal layers **4** and **9** by a chemical vapor deposition (CVD) process. The dielectric layer **85** can be a single layer of titanium dioxide (TiO_2), tantalum pentoxide (Ta_2O_5), silicon nitride (Si_3N_4), silicon dioxide (SiO_2) or a polymer, or a composite layer made of the previously described materials. The dielectric layer **85** has a thickness t**8** larger than 10 angstroms, such as between 10 and 50 angstroms, between 50 and 1,000 angstroms or between 100 and 10,000 angstroms.

[0864] Next, referring to FIG. **32**F, a photoresist layer **86**, such as positive-type photoresist layer or negative-type photoresist layer, is formed on the dielectric layer **85** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **86** is patterned with the processes of exposure and development, and a 1× stepper or 1× contact aligner can be used to expose the photoresist layer **86** during the process of exposure. Next, referring to FIG. **32**G, the dielectric layer **85** not under the photoresist layer **86** is removed with a dry etching method, such as enhanced plasma etching method.

[0865] Next, referring to FIG. **32**H, the photoresist layer **86** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **86** could remain on the bulk metal layer **9**. Thereafter, the residuals can be removed from the bulk metal layer **9** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0866] Referring to FIG. **32**I, after removing the polymer layer **86**, a polymer layer **14** is formed on the insulating layer **3**, on the dielectric layer **85** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and multiple openings **14***a* in the polymer layer **14** expose the dielectric layer **85** and the bulk metal layer **9**. The polymer layer **14** may have a thickness larger than 2 micrometers, such as between 3 and 50 micrometers, and preferably between 5 and 25 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin. The process of forming the polymer layer **14** and the openings **14***a* in the polymer layer **14** as shown in FIG. **32**I can be referred to as the process of forming the polymer layer **14** and the opening **14***a* in the polymer layer **14** as illustrated in FIG. **25**G.

[0867] Next, referring to FIG. **32**J, an adhesion/barrier layer **64** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **14**, on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* and on the dielectric layer **85** exposed by the opening **14***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **65** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **64** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **64** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **65** may include copper, nickel, aluminum, gold, platinum, silver or palladium.

[0868] For example, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 microme-

ters, on the polymer layer **14**, on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* and on the dielectric layer **85** exposed by the opening **14***a*, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0869] Alternatively, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the polymer layer **14**, on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* and on the dielectric layer **85** exposed by the opening **14***a* and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-tungsten-alloy layer.

[0870] Alternatively, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14**, on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* and on the dielectric layer **85** exposed by the opening **14***a*, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0871] Alternatively, when the adhesion/barrier layer **64** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **14**, on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a* and on the dielectric layer **85** exposed by the opening **14***a*, the seed layer **65** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0872] Referring to FIG. **32**K, after forming the seed layer **65**, a photoresist layer **67**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1 micrometer, such as between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, is formed on the seed layer **65** of any previously described material by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **67** is patterned with the processes of exposure and development to form two openings **67***a* in the photoresist layer **67** exposing the seed layer **65** of any previously described material. The process of forming the photoresist layer **67** and forming the two openings **67***a* in the photoresist layer **67** as shown in FIG. **32**K can be referred to as the process of forming the photoresist layer **67** and forming the openings **67***a* in the photoresist layer **67** as illustrated in FIG. **27**J.

[0873] Next, referring to FIG. **32**L, a metal layer **68** having a thickness larger than 1 micrometer, such as between 1 and 50 micrometers, and preferably between 2 and 20 micrometers, can be electroplated in the two openings **67***a* and on the seed layer **65** of any previously described material exposed by the two openings **67***a*. The metal layer **68** may be a single layer of gold, copper, silver, palladium, platinum, rhodium, ruthenium, rhenium or nickel, or a composite layer made of the previously described metals. The process of forming the metal layer **68** as shown in FIG. **32**L can be referred to as the process of forming the metal layer **68** as illustrated in FIG. **27**K. The specification of the metal layer **68** shown in FIG. **32**L can be referred to as the specification of the metal layer **68** as illustrated in FIG. **27**K.

[0874] Referring to FIG. **32**M, after forming the metal layer **68** is formed, the photoresist layer **67** can be removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **67** could remain on the metal layer **68** and on the seed layer **65** not under the metal layer **68**. Thereafter, the residuals can be removed from the metal layer **68** and from the seed layer **65** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0875] Next, referring to FIG. **32**N, the seed layer **65** and the adhesion/barrier layer **64** not under the metal layer **68** are subsequently removed with an etching method, which can be referred to as the step illustrated in FIG. **27**M. Accordingly, the capacitor **87** and the metal interconnect **88***b* can be formed on the insulating layer **3** of the semiconductor wafer **10** and at the backside **1***a* of the thinned silicon substrate **1**. The metal interconnect **88***b* at the backside **1***a* of the thinned silicon substrate **1** can be provided by the metal layers **9** and **68** or provided by the metal layer **9**. The metal interconnect **88***b* can be connected to the voltage regulator or converter circuit **41** through the bulk metal layer **9** in the through-silicon via **11***a* and through the fine-line metal structure **619**, and can be connected to the previously described inductor **36**.

[0876] The capacitor **87** at the backside **1***a* of the thinned silicon substrate **1** can be composed of a lower plate **87***a*, an upper plate **87***b* over the lower plate **87***a* and the dielectric layer **85** between the lower plate **87***a* and the upper plate **87***b*. The lower plate **87***a* composed of the metal layer **4** and the bulk metal layer **9** can be connected to the voltage regulator or the converter circuit **41** through the bulk metal layer **9** in the through-silicon via **11***f* and through the fine-line metal trace **619'**. The upper plate **87***b* composed of the adhesion/barrier layer **64**, the seed layer **65** and the metal layer **68** can be

connected to the internal circuits **22** and **23** through the bulk metal layer **9** in the through-silicon via **11***d* and through the fine-line metal trace **622** and to the internal circuit **24** through the bulk metal layer **9** in the through-silicon via **11***e* and through the fine-line metal trace **624**.

[0877] In FIG. **32**N, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the capacitor **87**, the metal interconnect **88***b*, the polymer layer **14** and the dielectric layer **85**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**.

[0878] After forming the structure shown in FIG. **32**N, using a die-sawing process, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, there is no metal bump or wirebonded wire formed on the metal layer **68** of the semiconductor chip for connecting the capacitor **87** or the metal interconnect **88***b* to an external circuit.

[0879] Alternatively, in the chip package, there is a first wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on the metal layer **68** of the metal interconnect **88***b* of the semiconductor chip for connecting the metal interconnect **88***b* to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and there is a second wirebonded wire, such as gold wirebonded wire or copper wirebonded wire, bonded on the metal layer **68** of the semiconductor chip for connecting the capacitor **87** to a ground bus or plane of the first external circuit or to a ground bus or plane of a second external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate.

[0880] Alternatively, in the chip package, there is a first metal bump, such as gold bump, copper bump, nickel bump or solder bump, connected to the metal layer **68** of the metal interconnect **88***b* of the semiconductor chip for connecting the metal interconnect **88***b* to a power bus or plane of a first external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and there is a second metal bump, such as gold bump, copper bump, nickel bump or solder bump, connected to the metal layer **68** of the semiconductor chip for connecting the capacitor **87** to a ground bus or plane of the first external circuit or to a ground bus or plane of a second external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate.

[0881] In the following, FIGS. **32**O-**32**R show a process for forming two metal bumps or pillars **27** over the metal layer **68** of the semiconductor wafer **10** for being used to connect the metal interconnect **88***b* to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, and connect the capacitor **87** to the first external circuit or to a second external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate.

[0882] Referring to FIG. **32**O, after the step illustrated in FIG. **32**N, a polymer layer **143** can be formed on the polymer layer **14** and on the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and two openings **143***a* in the polymer layer **143** are over two regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** and expose them. The polymer layer **143** has a thickness larger than 2 micrometers, such as between 3 and 50 micrometers, and preferably between 5 and 25 micrometers. The material of the polymer layer **143** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin. The process of forming the polymer layer **143** and the two openings **143***a* in the polymer layer **143** as shown in FIG. **32**O can be referred to as the process of forming the polymer layer **14** and the openings **14***a* in the polymer layer **14** as illustrated in FIG. **27**N. The specification of the polymer layer **143** shown in FIG. **32**O can be referred to as the specification of the polymer layer **14** as illustrated in FIG. **27**N.

[0883] Next, referring to FIG. **32**P, an adhesion/barrier layer **16** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **143** and on the two regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the two openings **143***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **18** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **16** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **16** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **18** may include copper, nickel, aluminum, gold, silver, platinum or palladium. The process of forming the adhesion/barrier layer **16** on the polymer layer **143** and on the two regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the two openings **143***a* and forming the seed layer **18** on the adhesion/barrier layer **16** as shown in FIG. **32**P can be referred to as the process of forming the adhesion/barrier layer **16** on the polymer layer **14** and on the regions of the topmost layer of gold, copper, nickel or palladium of the previously described various metal layer **68** exposed by the openings **14***a*' and forming the seed layer **18** on the adhesion/barrier layer **16** as illustrated in FIG. **27**O. The specification of the adhesion/barrier layer **16** and the seed layer **18** as shown in FIG. **32**P can be referred to as the specification of the adhesion/barrier layer **16** and the seed layer **18** as illustrated in FIG. **27**O, respectively.

[0884] Referring to FIG. **32**Q, after the step illustrated in FIG. **32**P, a photoresist layer **31** can be formed on the seed layer **18** of any previously described material, and two openings **31** a in the photoresist layer **31** expose the seed layer **18** of any previously described material, which can be referred to as the step illustrated in FIG. **25**I. Next, the two metal bumps or pillars **27** can be formed on the seed layer **18** of any

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previously described material exposed by the two openings **31***a* and in the two openings **31***a*. The process of forming the two metal bumps or pillars **27** on the seed layer **18** of any previously described material exposed by the two openings **31***a* and in the two openings **31***a* as shown in FIG. **32**Q can be referred to as the process of forming the metal bump or pillar **27** on the seed layer **18** of any previously described material exposed by the opening **31***a* and in the opening **31***a* as illustrated in FIG. **25**J. The specification of the two metal bumps or pillars **27** shown in FIG. **32**Q can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J.

[0885] Next, referring to FIG. **32**R, the photoresist layer **31** is removed, which can be referred to as the step illustrated in FIG. **25**K. Next, the seed layer **18** not under the two metal bumps or pillars **27** is removed, and then the adhesion/barrier layer **16** not under the two metal bumps or pillars **27** is removed, which can be referred to as the step illustrated in FIG. **25**L. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the capacitor **87**, the metal interconnect **88***b*, the polymer layers **14** and **143**, the dielectric layer **85**, the metal layers **16** and **18**, and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**, and the openings **143***a* in the polymer layer **143** are over the bulk metal layer **68**. After the step illustrated in FIG. **32**R, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0886] Alternatively, after the step illustrated in FIG. **32**R, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0887] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **32**A-**32**R. After the steps illustrated in FIGS. **32**A-**32**R, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0888] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, a first metal bump or pillar **27** connected to the metal layer **68** of the metal interconnect **88***b* of the semiconductor chip can connect the metal interconnect **88***b* and the previously described inductor **36** to a power bus or plane of the first external circuit to receive an external power voltage Vdd from the external circuit, and a second metal bump or pillar **27** connected to the metal layer **68** of the semiconductor chip can connect the capacitor **87** to a ground bus or plane of the first or second external circuit.

[0889] FIGS. **32**S and **32**T are cross sectional views showing a process for forming a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. Referring to FIG. **32**S, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**J is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the capacitor **87**, the metal interconnect **88***b*, the two metal bumps or pillars **27** and the polymer layers **14** and **143** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **32**A-**32**R. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **32**R can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0890] Referring to FIG. **32**T, after forming the structure shown in FIG. **32**S, the flux **32** is removed. Next, using the steps illustrated in FIGS. **15**D-**15**H, multiple patterned circuit layers **812** composed of an adhesion/barrier/seed layer **8121** and a metal layer **8122** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519** and **519'**, and a patterned circuit layer **821** composed of an adhesion/barrier/seed layer **8211** and a metal layer **8212** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**. Next, a polymer layer **98** is formed on the metal layer **8122** of the patterned circuit layers **812**, on the metal layer **8212** of the patterned circuit layer **821** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points of the metal layers **8122** and **8212** and expose them, which can be referred to as the step illustrated in FIG. **15**I. Next, multiple metal bumps **89** provided by triple metal layers **89***a*, **89***b* and **89***c* are formed on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, which can be referred to as the step illustrated in FIG. **30**L. The specification of the metal bumps **89** shown in FIG. **32**T can be referred to as the specification of the metal bumps **89** as illustrated in FIG. **30**L. Accordingly, an over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**. Alternatively, each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**.

[0891] After forming the structure shown in FIG. **32**T, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0892] In the chip package, for example, a first metal bump or pillar **27** connected to the metal layer **68** of the metal interconnect **88***b* of the semiconductor chip may connect the metal interconnect **88***b* and the previously described inductor **36** to a power bus or plane of a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and a second metal bump or pillar **27**

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connected to the metal layer **68** of the semiconductor chip may connect the capacitor **87** to a ground bus or plane of the first external circuit. A first metal bump **89** connected the metal trace, bus or plane **81** of the semiconductor chip may be connected to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal bumps **89** connected to the ground plane, bus or trace **82** of the semiconductor chip may be connected to a ground bus or plane of the second external circuit.

[0893] Alternatively, in the chip package, a first metal bump **89** connected to the metal trace, bus or plane **81**P of the semiconductor chip may be connected to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump **89** connected the metal trace, bus or plane **81** of the semiconductor chip may be connected to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal bumps **89** connected to the ground plane, bus or trace **82** of the semiconductor chip may be connected to a ground bus or plane of the first external circuit. A metal bump or pillar **27** connected to the metal layer **68** of the semiconductor chip may connect the capacitor **87** to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate.

[0894] FIG. **32**U is a cross sectional view showing a process for forming a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**M is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate I. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the capacitor **87**, the metal interconnect **88***b*, the two metal bumps or pillars **27** and the polymer layers **14** and **143** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **32**A-**32**R. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **32**R can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** can be performed after forming the two metal bumps or pillars **27**.

[0895] After forming the structure shown in FIG. **32**U, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0896] In the chip package, for example, a first metal bump or pillar **27** connected to the metal layer **68** of the metal interconnect **88***b* of the semiconductor chip may connect the metal interconnect **88***b* and the previously described inductor **36** to a power bus or plane of a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and a second metal bump or pillar **27** connected to the metal layer **68** of the semiconductor chip may connect the capacitor **87** to a ground bus or plane of the first external circuit. A first metal pad, bump or trace **34***a* connected the fine-line metal trace **619'** of the semiconductor chip may be connected to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal pads, bumps or traces **34***a* connected to the fine-line metal traces **621**, **622** and **624** of the semiconductor chip may be connected to a ground bus or plane of the second external circuit.

[0897] Alternatively, in the chip package, a first metal pad, bump or trace **34***a* connected to the fine-line metal trace **619** of the semiconductor chip may be connected to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal pad, bump or trace **34***a* connected to the fine-line metal trace **619'** of the semiconductor chip may be connected to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal pads, bumps or traces **34***a* connected to the fine-line metal traces **621**, **622** and **624** of the semiconductor chip may be connected to a ground bus or plane of the first external circuit. A metal bump or pillar **27** connected to the metal layer **68** of the semiconductor chip may connect the capacitor **87** to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate.

[0898] In the following, another process illustrate in FIGS. **33**A-**33**Y is introduced for forming the capacitor **87** in FIGS. **29**A, **29**B and **29**D. Referring to FIG. **33**A, the silicon substrate **1** of the semiconductor wafer **10** illustrated FIG. **30**A is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, multiple through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing multiple regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. The through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. The process of forming the through-silicon via **11***f* in the thinned silicon substrate **1** and in the dielectric layer **30** and forming the insulating layer **3** on the sidewall of the

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through-silicon via **11***f* as shown in FIG. **33**A can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* in the thinned silicon substrate **1** and in the dielectric layer(s) **30** and forming the insulating layer **3** on the sidewalls of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the metal layer **4** composed of the adhesion/barrier layer **4***a* and the seed layer **4***b* can be formed in the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the step illustrated in FIG. **25**A.

[0899] After forming the metal layer **4**, an anode **91** and a cathode **92** are formed on the seed layer **4***b* of the metal layer **4**. The material of the anode **91** may include polyaniline, active carbon, graphite, polypyrrole, carbon nanotube, a NiCo alloy or RuO_2. Alternatively, the anode **91** may be a composite layer including a nickel layer on the seed layer **4***b* of the metal layer **4** and a carbon layer on a top surface and sidewall of the nickel layer. The material of the cathode **92** may include polyaniline, active carbon, graphite, carbon nanotube or polypyrrole. For example, when the anode **91** is a NiCo alloy, the cathode **92** may be active carbon or carbon nanotube. Alternatively, the anode **91** and the cathode **92** can be porous. The anode **91** has a thickness t**9** larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers, and has a width d**2** larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers. The cathode **92** has a thickness t**10** larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers, and has a width d**3** larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers.

[0900] Referring to FIG. **33**B, after forming the anode **91** and the cathode **92**, a photoresist layer **29**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 1.5 micrometers, such as between 5 and 50 micrometers, and preferably between 10 and 25 micrometers, can be formed on the seed layer **4***b* of the metal layer **4**, on the anode **91** and on the cathode **92** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **29** is patterned with the processes of exposure and development to form multiple openings **29***a* in the photoresist layer **29** exposing the seed layer **4***b* of the metal layer **4**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **29** during the process of exposure. The process of forming the photoresist layer **29** on the seed layer **4***b* of the metal layer **4**, on the anode **91** and on the cathode **92** and forming the openings **29***a* in the photoresist layer **29** as shown in FIG. **33**B can be referred to as the process of forming the photoresist layer **29** on the seed layer **4***b* and forming the openings **29***a* in the photoresist layer **29** as illustrated in FIGS. **25**B-**25**C.

[0901] Next, referring to FIG. **33**C, a bulk metal layer **9** can be formed in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* by a process including an electroplating process. The process of forming the bulk metal layer **9** in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* as shown in FIG. **33**C can be referred to as the process of forming the bulk metal layer **9** in the openings **29***a* and on the seed layer **4***b* of the metal layer **4** exposed by the openings **29***a* as illustrated in FIG. **25**D. The specification of the bulk metal layer **9** shown in FIG. **33**C can be referred to as the specification of the bulk metal layer **9** as illustrated in FIG. **25**D.

[0902] Referring to FIG. **33**D, after the step illustrated in FIG. **33**C, the photoresist layer **29** can be removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **29** could remain on the bulk metal layer **9**, on the anode **91**, on the cathode **92** and on the seed layer **4***b* of the metal layer **4** not under the bulk metal layer **9**, the anode **91** and the cathode **92**. Thereafter, the residuals can be removed from the bulk metal layer **9**, from the anode **91**, from the cathode **92** and from the seed layer **4***b* of the metal layer **4** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen.

[0903] Next, referring to FIG. **33**E, the metal layer **4** not under the bulk metal layer **9**, the anode **91** and the cathode **92** is removed by etching the seed layer **4***b* not under the bulk metal layer **9**, the anode **91** and the cathode **92**, and then etching the adhesion/barrier layer **4***a* not under the bulk metal layer **9**, the anode **91** and the cathode **92**. The process of removing the seed layer **4***b* not under the bulk metal layer **9**, the anode **91** and the cathode **92** and removing the adhesion/barrier layer **4***a* not under the bulk metal layer **9**, the anode **91** and the cathode **92** as shown in FIG. **33**E can be referred to as the process of removing the seed layer **4***b* not under the bulk metal layer **9** and removing the adhesion/barrier layer **4***a* not under the bulk metal layer **9** as illustrated in FIG. **25**F.

[0904] Accordingly, the anode **91** and the cathode **92** are formed over the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, and the previously described metal traces **88***a*, **88***b* and **88***c* provided by the metal layers **4** and **9** are formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**. FIG. **33**F is a top view of FIG. **33**E. Referring to FIGS. **33**E and **33**F, the cathode **92** has multiple parallel lines **125** extending into gaps between multiple parallel lines **124** of the anode **91**. The anode **91** is connected to the node P of the voltage regulator or converter circuit **41** and the previously described inductor **36** through the metal trace **88***c*. The cathode **92** is connected to the ground node Rs of the voltage regulator or converter circuit **41** and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. The horizontal space d**4** between the neighboring lines **124** and **125** of the cathode **92** and anode **91** can be larger than 0.1 micrometers, such as between 0.1 and 10 micrometers, and preferably between 1 and 5 micrometers.

[0905] Referring to FIG. **33**G, after the step illustrated in FIG. **33**E, a polymer layer **14** can be formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process. An opening **14***b* in the polymer layer **14** exposes the anode **91** and the cathode **92**, and the anode **91** and the cathode **92** are on the insulating layer **3** and in the opening **14***b*. The polymer layer **14** may have a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin. The process of forming the polymer layer **14** and the opening **14***b* in the polymer layer **14** as shown in FIG. **33**G can be referred to as the process of forming the polymer layer **14** and the opening **14***a* in the polymer layer **14** as illustrated in FIG. **25**G.

[0906] FIG. **33**I is a top view of FIG. **33**H. Referring to FIGS. **33**H and **33**I, a jelly electrolyte **93**, containing a polymer and metal ions, such as Li^+, Ni^+ or Cu^+, is formed in the opening **14***b* in the polymer layer **14**, on the insulating layer **3** exposed by the opening **14***b* and in the gaps between the parallel lines **124** and **125**, and covers top surfaces of the anode **91** and the cathode **92**. After forming the jelly electrolyte **93**, a super capacitor **87** including the anode **91**, the cathode **92** and the jelly electrolyte **93** can be formed on the insulating layer **3** and in the opening **14***b* in the polymer layer **14**. The super capacitor **87** at the backside **1***a* of the thinned silicon substrate **1** has capacitance in the range of between 0.01 and 100 microfarads, and has energy storage capability in the range of between 0.1 and 10 microfarads per square meter ($\mu F/mm^2$). The area of the super capacitor **87**, enclosed by the bold line shown in FIG. **33**I, is in the range of between 0.1 and 10 square meters. Alternatively, the jelly electrolyte **93** can be replaced by a liquid electrolyte containing a polymer and metal ions, such as Li^+, Ni^+ or Cu^+. The capacitor **87** is reversibly chargeable and dischargeable.

[0907] Referring to FIG. **33**J, a polymer layer **133** is formed on the polymer layer **14** and covers the jelly electrolyte **93** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process. The polymer layer **133** may have a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers. The material of the polymer layer **133** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0908] Referring to FIG. **33**K, a top surface of the polymer layer **133** can be optionally polished by a chemical mechanical polishing (CMP) process or a mechanical polishing process, leading the polymer layer **133** to have a top surface **133***s* substantially coplanar with a top surface **14***s* of the polymer layer **14**. Accordingly, a bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**, and includes the insulating layer **3**, the capacitor **87** composed of the anode **91**, the cathode **92** and the jelly electrolyte **93**, the metal traces **88***a*, **88***b* and **88***c*, and the polymer layers **14** and **133**, and the opening **14***b* in the polymer layer **14** is over the insulating layer **3**.

[0909] After the step illustrated in FIG. **33**K, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0910] FIG. **33**L is a cross sectional view showing a semiconductor wafer **10** illustrated in FIG. **33**K with an over-passivation scheme **102** over the passivation layer **5** at the active side of the thinned silicon substrate **1**, which can be formed by a suitable process or processes, e.g., by the following steps. First, multiple openings **519**, **519'**, **521**, **522** and **524** are formed in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or pads **600** after the step illustrated in FIG. **33**K. The openings **519**, **519'**, **521**, **522** and **524** are over the regions **600***a*, and the regions **600***a* are at bottoms of the openings **519**, **519'**, **521**, **522** and **524**. Next, using the steps illustrated in FIGS. **15**D-**15**H, multiple patterned circuit layers **812** composed of an adhesion/barrier/seed layer **8121** and a metal layer **8122** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519** and **519'**, and a patterned circuit layer **821** composed of an adhesion/barrier/seed layer **8211** and a metal layer **8212** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**. Next, a polymer layer **98** is formed on the metal layer **8122** of the patterned circuit layers **812**, on the metal layer **8212** of the patterned circuit layer **821** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points of the metal layers **8122** and **8212** and expose them, which can be referred to as the step illustrated in FIG. **15**I. Next, multiple metal bumps **89** provided by triple metal layers **89***a*, **89***b* and **89***c* are formed on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, which can be referred to as the step illustrated in FIG. **30**L. The specification of the metal bumps **89** shown in FIG. **33**L can be referred to as the specification of the metal bumps **89** as illustrated in FIG. **30**L. Accordingly, the over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**.

[0911] After forming the structure shown in FIG. **33**L, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, a first metal bump **89** can connect the metal trace, bus or plane **81**P of the semiconductor chip to an external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the external circuit, and can be connected to the metal trace **88***b* at the backside **1***a* of the thinned silicon substrate **1** and the voltage regulator or converter circuit **41** through the metal trace, bus or plane **81**P at the active side of the thinned silicon substrate **1** and through the fine-line metal trace **619**. A second metal bump **89** can connect the metal trace, bus or plane **81** of the semiconductor chip to the external circuit to output a regulated or converted power voltage Vcc to the external circuit, and can be connected to the metal trace **88***c* at the backside **1***a* of the thinned silicon substrate **1** and the voltage regulator or converter circuit **41** through the metal trace, bus or plane **81** at the active side of the thinned silicon substrate **1** and through the fine-line metal trace **619'**. Multiple third metal bumps **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the external circuit, and can be connected to the metal trace **88***a* at the backside **1***a* of the thinned silicon substrate **1** and the internal circuits **21**, **22**, **23** and **24** through the ground plane, bus or trace **82** at the active side of the thinned silicon substrate **1**.

[0912] FIG. **33**M is a cross sectional view showing a semiconductor wafer **10** illustrated in FIG. **33**K with metal pads, bumps or traces at the active side of the thinned silicon substrate **1**, which can be formed by a suitable process or processes, e.g., by the following steps. First, multiple openings **519**, **519'**, **521**, **522** and **524** are formed in the passivation layer **5** to expose multiple regions **600***a* of the metal traces or

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pads **600** after the step illustrated in FIG. **33**K. The openings **519**, **519'**, **521**, **522** and **524** are over the regions **600***a*, and the regions **600***a* are at bottoms of the openings **519**, **519'**, **521**, **522** and **524**. Next, multiple metal pads, bumps or traces **34***a* provided by two metal layers **32** and **34** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524**. The process of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** as shown in FIG. **33**M can be referred to as the process of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **531**, **532**, **534**, **539** and **539'** as illustrated in FIG. **25**N. The specification of the metal pads, bumps or traces **34***a* shown in FIG. **33**M can be referred to as the specification of the metal pads, bumps or traces **34***a* as illustrated in FIG. **25**N.

[0913] After forming the structure shown in FIG. **33**M, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, a first metal pad, bump or trace **34***a* can connect the fine-line metal trace **619** of the semiconductor chip to an external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the external circuit, and can be connected to the metal trace **88***b* at the backside **1***a* of the thinned silicon substrate **1** and the voltage regulator or converter circuit **41** through the fine-line metal trace **619**. A second metal pad, bump or trace **34***a* can connect the fine-line metal trace **619'** of the semiconductor chip to the external circuit to output a regulated or converted power voltage Vcc to the external circuit, and can be connected to the metal trace **88***c* at the backside **1***a* of the thinned silicon substrate **1** and the voltage regulator or converter circuit **41** through the fine-line metal trace **619'**. Multiple third metal pads, bumps or traces **34***a* can connect the fine-line metal traces **621**, **622** and **624** of the semiconductor chip to a ground bus or plane of the external circuit, and can be connected to the metal trace **88***a* at the backside **1***a* of the thinned silicon substrate **1** through the fine-line metal traces **621**, **622** and **624**.

[0914] FIGS. **33**N-**33**S show a process of forming a super capacitor **87** and multiple metal bumps or pillars **27** at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **33**E.

[0915] Referring to FIG. **33**N, after the step illustrated in FIG. **33**E, a polymer layer **14** can be formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process. An opening **14***a* in the polymer layer **14** is over a region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** of the metal trace **88***b* and exposes it, an opening **14***c* in the polymer layer **14** is over a region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** of the metal trace **88***a* and exposes it, and an opening **14***d* in the polymer layer **14** is over a region of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** of the metal trace **88***c* and exposes it. An opening **14***b* in the polymer layer **14** exposes the anode **91** and the cathode **92**, and the anode **91** and the cathode **92** are in the opening **14***b* and over the insulating layer **3**. The polymer layer **14** may have a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin. The process of forming the polymer layer **14** and the openings **14***a*, **14***b*, **14***c* and **14***d* in the polymer layer **14** as shown in FIG. **33**N can be referred to as the process of forming the polymer layer **14** and the opening **14***a* in the polymer layer **14** as illustrated in FIG. **25**G.

[0916] FIG. **33**P is a top view of FIG. **330**. Referring to FIGS. **330** and **33**P, a jelly electrolyte **93**, containing a polymer and metal ions, such as Li^+, Ni^+ or Cu^+, is formed in the opening **14***b* in the polymer layer **14**, on the insulating layer **3** exposed by the opening **14***b* and in the gaps between the parallel lines **124** and **125**, and covers top surfaces of the anode **91** and the cathode **92**. After forming the jelly electrolyte **93**, the super capacitor **87** including the anode **91**, the cathode **92** and the jelly electrolyte **93** can be formed on the insulating layer **3** and in the opening **14***b* in the polymer layer **14**. The super capacitor **87** at the backside **1***a* of the thinned silicon substrate **1** has capacitance in the range of between 0.01 and 100 microfarads, and has energy storage capability in the range of between 0.1 and 10 microfarads per square meter ($\mu F/mm^2$). The area of the super capacitor **87**, enclosed by the bold line shown in FIG. **33**P, is in the range of between 0.1 and 10 square meters. Alternatively, the jelly electrolyte **93** can be replaced by a liquid electrolyte containing a polymer and metal ions, such as Li^+, Ni^+ or Cu^+. The capacitor **87** is reversibly chargeable and dischargeable.

[0917] Next, referring to FIG. **33**Q, a polymer layer **133** is formed on the polymer layer **14** and covers the jelly electrolyte **93** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and multiple openings **133***a* in the polymer layer **133** are over the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d* and expose them. The polymer layer **133** has a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers. The material of the polymer layer **133** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0918] In a case, the polymer layer **133** can be formed by a suitable process or processes, e.g., by spin-on coating a negative-type photosensitive polyimide layer having a thickness between 6 and 50 micrometers on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, on the polymer layer **14** and on the jelly electrolyte **93**, then baking the spin-on coated polyimide layer, then exposing the baked polyimide layer using a 1× stepper or a 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polyimide layer, that is, G-line and H-line, G-line and I-line, H-line and

I-line, or G-line, H-line and I-line illuminate the baked polyimide layer, then developing the exposed polyimide layer to form multiple openings exposing the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, then curing or heating the developed polyimide layer at a temperature between 100 and 150° C. for a time between 20 and 150 minutes in a nitrogen ambient or in an oxygen-free ambient, the cured polyimide layer having a thickness between 3 and 25 micrometers, and then removing the residual polymeric material or other contaminants from the bulk metal layer **9** of the metal trace **130** with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By the way, the polymer layer **133** is formed on the polymer layer **14** and covers the jelly electrolyte **93**, and the openings **133***a* formed in the polymer layer **133** expose the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*. Alternatively, the developed polyimide layer can be cured or heated using ultraviolet.

[0919] In another case, the polymer layer **133** can be formed by a suitable process or processes, e.g., by spin-on coating a positive-type photosensitive polybenzoxazole layer having a thickness between 3 and 25 micrometers on the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, on the polymer layer **14** and on the jelly electrolyte **93**, then baking the spin-on coated polybenzoxazole layer, then exposing the baked polybenzoxazole layer using a 1× stepper or a 1× contact aligner with at least two of G-line having a wavelength ranging from, e.g., about 434 to 438 nm, H-line having a wavelength ranging from, e.g., about 403 to 407 nm, and I-line having a wavelength ranging from, e.g., about 363 to 367 nm, illuminating the baked polybenzoxazole layer, that is, G-line and H-line, G-line and I-line, H-line and I-line, or G-line, H-line and I-line illuminate the baked polybenzoxazole layer, then developing the exposed polybenzoxazole layer to form multiple openings exposing the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, then curing or heating the developed polybenzoxazole layer at a temperature between 100 and 150° C. for a time between 5 and 180 minutes, and preferably between 30 and 120 minutes, in a nitrogen ambient or in an oxygen-free ambient, the cured polybenzoxazole layer having a thickness between 3 and 25 micrometers, and then removing the residual polymeric material or other contaminants from the bulk metal layer **9** of the metal trace **130** with an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. By the way, the polymer layer **133** is formed on the polymer layer **14** and covers the jelly electrolyte **93**, and the openings **133***a* formed in the polymer layer **133** expose the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*. Alternatively, the developed polybenzoxazole layer can be cured or heated using ultraviolet.

[0920] Referring to FIG. **33**R, after the step illustrated in FIG. **33**Q, an adhesion/barrier layer **16** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **133**, on the polymer layer **14** and on the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. Next, a seed layer **18** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **16** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **16** may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **18** may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0921] For example, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **133**, on the polymer layer **14** and on the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0922] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the polymer layer **133**, on the polymer layer **14** and on the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d* and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-tungsten-alloy layer.

[0923] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **133**, on the polymer layer **14** and on the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0924] Alternatively, when the adhesion/barrier layer **16** is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **133**,

on the polymer layer **14** and on the regions of the bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*, the seed layer **18** can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0925] After forming the seed layer **18**, a photoresist layer **31** can be formed on the seed layer **18** of any previously described material, and multiple openings **31***a* in the photoresist layer **31** expose the seed layer **18** of any previously described material, which can be referred to as the step illustrated in FIG. **25**I. The openings **31***a* are over the regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** exposed by the openings **14***a*, **14***c* and **14***d*. Next, the metal bumps or pillars **27** can be formed on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a*. The process of forming the metal bumps or pillars **27** on the seed layer **18** of any previously described material exposed by the openings **31***a* and in the openings **31***a* as shown in FIG. **33**R can be referred to as the process of forming the metal bump or pillar **27** on the seed layer **18** of any previously described material exposed by the opening **31***a* and in the opening **31***a* as illustrated in FIG. **25**J. The specification of the metal bumps or pillars **27** shown in FIG. **33**R can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J.

[0926] Next, referring to FIG. **33**S, the photoresist layer **31** is removed, which can be referred to as the step illustrated in FIG. **25**K. Next, the seed layer **18** not under the metal bumps or pillars **27** is removed, and then the adhesion/barrier layer **16** not under the metal bumps or pillars **27** is removed, which can be referred to as the step illustrated in FIG. **25**L. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the capacitor **87** composed of the anode **91**, the cathode **92** and the jelly electrolyte **93**, the metal traces **88***a*, **88***b* and **88***c*, the polymer layers **14** and **133**, the metal layers **16** and **18**, and the metal bumps or pillars **27**, and the openings **14***a*, **14***c* and **14***d* in the polymer layer **14** are over the bulk metal layer **9**, the opening **14***b* in the polymer layer **14** is over the insulating layer **3**, and the openings **133***a* in the polymer layer **133** are over the bulk metal layer **9**. After the step illustrated in FIG. **33**S, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0927] Alternatively, after the step illustrated in FIG. **33**S, with the following steps being illustrated with reverse figures for simple explanation, multiple openings **50** are formed in the passivation layer **5** to expose the metal traces or pads **600**, and then each of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** can be alternatively formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**. Thereafter, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0928] Alternatively, a process of forming any one of the over-passivation schemes **102** illustrated in FIGS. **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H and **20** over the passivation layer **5** can be performed before the steps illustrated in FIGS. **33**A-**33**E and **33**N-**33**S. After the steps illustrated in FIGS. **33**A-**33**E and **33**N-**33**S, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process.

[0929] After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package. In the chip package, for example, a first metal bump or pillar **27** can connect the metal trace **88***b* and the previously described inductor **36** of the semiconductor chip to an external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the external circuit, and can be connected to the previously described inductor **36** and the voltage regulator or converter circuit **41** through the metal trace **88***b*. A second metal bump or pillar **27** can connect the metal trace **88***c* of the semiconductor chip to the external circuit to output a regulated or converted power voltage Vcc to the external circuit. The second metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'**, and to the previously described inductor **36** and the anode **91** of the capacitor **87** through the metal trace **88***c*. A third metal bump or pillar **27** can connect the metal trace **88***a*, and the capacitor **87** of the semiconductor chip to a ground bus or plane of the external circuit, and can be connected to the cathode **92** of the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*.

[0930] FIG. **33**T is a cross sectional view showing a process for forming a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**J is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the capacitor **87**, the metal interconnect **88***a*, **88***b* and **88***c*, the metal bumps or pillars **27** and the polymer layers **14** and **143** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **33**A-**33**E and **33**N-**33**S. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **33**S can be formed at the backside **1***a* of the thinned silicon substrate **1**.

[0931] After forming the structure shown in FIG. **33**T, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the flux **32** of the semiconductor chip cut from the semiconductor wafer **10** is removed, and then the semiconductor chip is packaged for a chip package. In the chip package, the metal bumps or pillars **27** of the bottom scheme **103** of the semiconductor chip can be connected to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, and multiple wirebonded wires, such as gold wirebonded wires, aluminum wirebonded

wires or copper wirebonded wires, can be boned with the regions **600***a* of copper or aluminum of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524**. The wirebonded wires can connect the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** to the first external circuit or a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate.

[0932] In the chip package, for example, a first metal bump or pillar **27** can connect the metal trace **88***b*, the voltage regulator or converter circuit **41** and the previously described inductor **36** of the semiconductor chip to a power bus or plane of a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and the first metal bump or pillar **27** is connected to the voltage regulator or converter circuit **41** through the metal trace **88***b* and the fine-line metal trace **619**. A second metal bump or pillar **27** can connect the metal trace **88***c* of the semiconductor chip to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. The second metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'**, and to the previously described inductor **36** and the anode **91** of the capacitor **87** through the metal trace **88***c*. A third metal bump or pillar **27** can connect the metal trace **88***a*, the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to a ground bus or plane of the first external circuit, and the third metal bump **27** is connected to the cathode **92** of the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. A first wirebonded wire, such as gold wirebonded wire, aluminum wirebonded wire or copper wirebonded wire, is boned with the region **600***a* of copper or aluminum of the metal trace or pad **600** exposed by the opening **519'**, and connects the fine-line metal trace **619'** and the voltage regulator or converter circuit **41** of the semiconductor chip to the first external circuit or a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc. Multiple second wirebonded wires, such as gold wirebonded wires, aluminum wirebonded wires or copper wirebonded wires, are boned with the regions **600***a* of copper or aluminum of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**, and connect the fine-line metal traces **621**, **622** and **624** and the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to a ground bus or plane of the first or second external circuit.

[0933] Alternatively, in the chip package, a first wirebonded wire, such as gold wirebonded wire, aluminum wirebonded wire or copper wirebonded wire, is boned with the region **600***a* of copper or aluminum of the metal trace or pad **600** exposed by the opening **519**, and connects the fine-line metal trace **619** and the voltage regulator or converter circuit **41** of the semiconductor chip to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second wirebonded wire, such as gold wirebonded wire, aluminum wirebonded wire or copper wirebonded wire, is boned with the region **600***a* of copper or aluminum of the metal trace or pad **600** exposed by the opening **519'**, and connects the fine-line metal trace **619'** and the voltage regulator or converter circuit **41** to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third wirebonded wires, such as gold wirebonded wires, aluminum wirebonded wires or copper wirebonded wires, are boned with the regions **600***a* of copper or aluminum of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**, and connect the fine-line metal traces **621**, **622** and **624** and the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to a ground bus or plane of the first external circuit. A first metal bump or pillar **27** can connect the metal trace **88***a* and the capacitor **87** of the semiconductor chip to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, and can be connected to the cathode **92** of the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. A second metal bump or pillar **27** can connect the metal trace **88***c* of the semiconductor chip to the second external circuit to output the regulated or converted power voltage Vcc to the second external circuit. The second metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'**, and to the previously described inductor **36** and the anode **91** of the capacitor **87** through the metal trace **88***c*.

[0934] FIG. **33**U is a cross sectional view showing a process for forming a semiconductor wafer, which can be formed by a suitable process or processes, e.g., by the following steps. First, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**M is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. Next, the structure including the capacitor **87**, the metal interconnect **88***a*, **88***b* and **88***c*, the metal bumps or pillars **27** and the polymer layers **14** and **143** can be formed in the through silicon vias **11***a*, **11***d*, **11***e* and **11***f* and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **33**A-**33**E and **33**N-**33**S. Accordingly, a bottom scheme **103** same as the bottom scheme **103** shown in FIG. **33**S can be formed at the backside **1***a* of the thinned silicon substrate **1**. Alternatively, the step of forming the metal pads, bumps or traces **34***a* on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** can be performed after forming the metal bumps or pillars **27**.

[0935] After forming the structure shown in FIG. **33**U, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0936] In the chip package, for example, a first metal bump or pillar **27** can connect the metal trace **88***b* and the previously described inductor **36** of the semiconductor chip to a power

bus or plane of a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***b* and the fine-line metal trace **619**. A second metal bump or pillar **27** can connect the metal trace **88***c* of the semiconductor chip to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. The second metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'**, and to the previously described inductor **36** and the anode **91** of the capacitor **87** through the metal trace **88***c*. A third metal bump or pillar **27** can connect the metal trace **88***a* and the capacitor **87** of the semiconductor chip to a ground bus or plane of the first external circuit, and can be connected to the cathode **92** of the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. A first metal pad, bump or trace **34***a* and the fine-line metal trace **619'** can connect the voltage regulator or converter circuit **41** of the semiconductor chip to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, by bonding the first metal pad, bump or trace **34***a* to the second external circuit or by wirebonding a gold wire, an aluminum wire or a copper wire to the first metal pad, bump or trace **34***a* and to the second external circuit, to output the regulated or converted power voltage Vcc to the second external circuit. Multiple second metal pads, bumps or traces **34***a* and the fine-line metal traces **621**, **622** and **624** can connect the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to a ground bus or plane of the second external circuit by bonding the second metal pads, bumps or traces **34***a* to the ground bus or plane of the second external circuit or by wirebonding multiple gold wires, multiple aluminum wires or multiple copper wires to the second metal pads, bumps or traces **34***a* and to the ground bus or plane of the second external circuit.

[0937] Alternatively, in the chip package, a first metal pad, bump or trace **34***a* and the fine-line metal trace **619** can connect the voltage regulator or converter circuit **41** of the semiconductor chip to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, by bonding the first metal pad, bump or trace **34***a* to the first external circuit or by wirebonding a gold wire, an aluminum wire or a copper wire to the first metal pad, bump or trace **34***a* and to the first external circuit, to receive an external power voltage Vdd from the first external circuit. A second metal pad, bump or trace **34***a* and the fine-line metal trace **619'** can connect the voltage regulator or converter circuit **41** of the semiconductor chip to the first external circuit by bonding the second metal pad, bump or trace **34***a* to the first external circuit or by wirebonding a gold wire, an aluminum wire or a copper wire to the second metal pad, bump or trace **34***a* and to the first external circuit, to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal pads, bumps or traces **34***a* and the fine-line metal traces **621**, **622** and **624** can connect the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to a ground bus or plane of the first external circuit by bonding the third metal pads, bumps or traces **34***a* to the ground bus or plane of the first external circuit or by wirebonding multiple gold wires, multiple aluminum wires or multiple copper wires to the third metal pads, bumps or traces **34***a* and to the ground bus or plane of the first external circuit. A first metal bump or pillar **27** can connect the metal trace **88***a* and the capacitor **87** of the semiconductor chip to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, and can be connected to the cathode **92** of the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. A second metal bump or pillar **27** can connect the metal trace **88***c* of the semiconductor chip to the second external circuit to output the regulated or converted power voltage Vcc to the second external circuit. The second metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'**, and to the previously described inductor **36** and the anode **91** of the capacitor **87** through the metal trace **88***c*.

[0938] FIG. **33**V shows a top view of another kind of capacitor **87**, and FIG. **33**W shows a cross sectional view cut along the dot line A-A in FIG. **33**V. Referring to FIGS. **33**V and **33**W, the capacitor **87** is formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10**. A shielding ring **123** provided by the metal layer **4** and the bulk metal layer **9** can be formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10** for containing the jelly electrolyte **93** of the capacitor **87**. Alternatively, the shielding ring **123** can be a polymer layer, such as polyimide layer, benzocyclobutane (BCB) layer, polybenzoxazole (PBO) layer or epoxy resin layer, or an inorganic layer, such as silicon-oxide layer, silicon-oxynitride layer or silicon-nitride layer, formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10**. The shielding ring **123** has a thickness larger than that of the anode **91** of the capacitor **87** and larger than that of the cathode **92** of the capacitor **87**, and has a top surface higher than that of the anode **91** of the capacitor **87** and higher than that of the cathode **92** of the capacitor **87**. The' anode **91** and the cathode **92** are in the jelly electrolyte **93** in the shielding ring **123**. The polymer layer **14** is formed on the jelly electrolyte **93**, on the shielding ring **123**, on the bulk metal layer **9** and on the insulating layer **3**, and covers the jelly electrolyte **93** and the shielding ring **123**.

[0939] The anode **91** of the capacitor **87** is connected to the bulk metal layer **9** of the metal trace **88***c*, and the cathode **92** of the capacitor **87** is connected to the bulk metal layer **9** of the metal trace **88***a*. The anode **91** of the capacitor **87** can be connected to the voltage regulator or converter circuit **41** and the previously described inductor **36** through the fine-line metal trace **619'** and the metal trace **88***c*. The cathode **92** of the capacitor **87** can be connected to the internal circuit **21** through the fine-line metal trace **621** and the metal trace **88***a*, to the internal circuits **22** and **23** through the fine-line metal trace **622** and the metal trace **88***a*, and to the internal circuit **24** through the fine-line metal traces **622** and **624** and the metal trace **88***a*.

[0940] Two metal bumps or pillars **27** can be formed over the bulk metal layer **9** and at the backside **1***a* of the thinned silicon substrate **1**. The left one metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***b*, through the bulk metal layer **9** in the through-silicon via **11***a* and through the fine-line metal structure **619**, and to the previously described inductor **36**

through the metal trace **88***b*. The right one metal bump or pillar **27** can be connected to the infernal circuit **21** through the bulk metal layer **9** in the through-silicon via **11***e*, through the fine-line metal traces **621**, **622** and **624** and through the metal trace **88***a*, to the internal circuits **22** and **23** through the bulk metal layer **9** in the through-silicon via **11***e* and through the fine-line metal traces **622** and **624**, and to the internal circuit **24** through the bulk metal layer **9** in the through-silicon via **11***e* and through the fine-line metal trace **624**.

[0941] In FIG. **33**W, a bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**, and includes the insulating layer **3**, the capacitor **87** composed of the anode **91**, the cathode **92** and the jelly electrolyte **93**, the metal trace **88***b*, the shielding ring **123**, the polymer layer **14**, the metal layers **16** and **18**, and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**. An over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**, and the openings **980** in the polymer layer **98** are under the patterned circuit layers **812** and **821**.

[0942] The specification of the anode **91**, the cathode **92** and the jelly electrolyte **93** as shown in FIGS. **33**V and **33**W can be referred to as the specification of the anode **91**, the cathode **92** and the jelly electrolyte **93**, respectively, as illustrated in FIGS. **33**A-**33**U. The specification of the metal bumps or pillars **27** shown in FIG. **33**W can be referred to as the specification of the metal bumps or pillars **27** as illustrated in FIGS. **25**G-**25**L and **33**N-**33**U. The process for forming the shielding ring **123** for containing the jelly electrolyte **93**, shown in FIGS. **33**V and **33**W, can be referred to as that for forming the metal layer **4** and the bulk metal layer **9** as illustrated in FIGS. **33**A-**33**E. The element in FIGS. **33**V and **33**W indicated by a same reference number as indicates the element in FIGS. **33**A-**33**U has a same material and spec as the element illustrated in FIGS. **33**A-**33**U.

[0943] After forming the structure shown in FIGS. **33**V and **33**W, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0944] In the chip package, for example, the left one metal bump or pillar **27** can connect the metal trace **88***b* and the previously described inductor **36** of the semiconductor chip to a power bus or plane of a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. The right one metal bump or pillar **27** can connect the cathode **92** of the capacitor **87** and the metal trace **88***a* of the semiconductor chip to a ground bus or plane of the first external circuit through the fine-line metal traces **622** and **624** and through the bulk metal layer **9** in the through-silicon via **11***e*, and can connect the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to the ground bus or plane of the first external circuit through the fine-line metal trace **624** and through the bulk metal layer **9** in the through-silicon via **11***e*. A first metal bump **89** can connect the metal trace, bus or plane **81** of the semiconductor chip to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output a regulated or converted power voltage Vcc to the second external circuit. Multiple second metal bumps **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the second external circuit.

[0945] Alternatively, in the chip package, a first metal bump **89** can connect the metal trace, bus or plane **81**P and the voltage regulator or converter circuit **41** of the semiconductor chip to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump **89** can connect the metal trace, bus or plane **81** and of the semiconductor chip to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal bumps **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the first external circuit. The right one metal bump or pillar **27** can connect the cathode **92** of the capacitor **87** and the metal trace **88***a* of the semiconductor chip to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, through the fine-line metal traces **622** and **624** and through the bulk metal layer **9** in the through-silicon via **11***e*, and can connect the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to the ground bus or plane of the second external circuit through the fine-line metal trace **624** and through the bulk metal layer **9** in the through-silicon via **11***e*.

[0946] FIG. **33**X shows a top view of another kind of capacitor **87**, and FIG. **33**Y shows a cross sectional view cut along the dot line A-A in FIG. **33**X. Referring to FIGS. **33**X and **33**Y, the capacitor **87** is formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10**. A shielding ring **123** provided by the metal layer **4** and the bulk metal layer **9** can be formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10** for containing the jelly electrolyte **93** of the capacitor **87**. Alternatively, the shielding ring **123** can be a polymer layer, such as polyimide layer, benzocyclobutane (BCB) layer, polybenzoxazole (PBO) layer or epoxy resin layer, or an inorganic layer, such as silicon-oxide layer, silicon-oxynitride layer or silicon-nitride layer, formed on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor wafer **10**. The shielding ring **123** has a thickness larger than that of the anode **91** of the capacitor **87** and larger than that of the cathode **92** of the capacitor **87**, and has a top surface higher than that of the anode **91** of the capacitor **87** and higher than that of the cathode **92** of the capacitor **87**. The anode **91** of the capacitor **87** is in the through-silicon via **11***f*, at the backside **1***a* of the thinned silicon substrate **1** and in the jelly electrolyte **93** in the shielding ring **123**. The cathode **92** of the capacitor **87** is in the through-silicon via **11***d*, at the backside **1***a* of the thinned silicon substrate **1**, and in the jelly electrolyte **93** in the shielding ring **123**. The polymer layer **14** is formed on the jelly electrolyte **93**, on the shielding ring **123**, on the bulk metal layer **9** and on the insulating layer **3**, and covers the jelly electrolyte **93** and the shielding ring **123**.

[0947] The anode **91** of the capacitor **87** can be connected to the voltage regulator or converter circuit **41** and the previously described inductor **36** through the fine-line metal trace **619'**. The cathode **92** of the capacitor **87** can be connected to the internal circuit **21** through the fine-line metal trace **621**, to

the internal circuits **22** and **23** through the fine-line metal trace **622**, and to the internal circuit **24** through the fine-line metal traces **622** and **624**.

[0948] Two metal bumps or pillars **27** are formed over the bulk metal layer **9** and at the backside **1***a* of the thinned silicon substrate **1**, and connect the bulk metal layer **9**. The left one metal bump or pillar **27** can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***b*, through the bulk metal layer **9** in the through-silicon via **11***a* and through the fine-line metal structure **619**, and to the previously described inductor **36** through the metal trace **88***b*. The right one metal bump or pillar **27** can be connected to the internal circuit **21** through the bulk metal layer **9** in the through-silicon via **11***e* and the fine-line metal traces **621**, **622** and **624**, to the internal circuits **22** and **23** through the bulk metal layer **9** in the through-silicon via **11***e* and the fine-line metal traces **622** and **624**, to the internal circuit **24** through the bulk metal layer **9** in the through-silicon via **11***e* and the fine-line metal trace **624**, and to the cathode **92** of the capacitor **87** through the bulk metal layer **9** in the through-silicon via **11***e* and the fine-line metal trace **624**.

[0949] In FIG. **33**Y, a bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**, and includes the insulating layer **3**, the capacitor **87** composed of the anode **91**, the cathode **92** and the jelly electrolyte **93**, the metal trace **88***b*, the shielding ring **123**, the polymer layer **14**, the metal layers **16** and **18**, and the metal bumps or pillars **27**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**. An over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**, and the openings **980** in the polymer layer **98** are under the patterned circuit layers **812** and **821**.

[0950] The specification of the anode **91**, the cathode **92** and the jelly electrolyte **93** as shown in FIGS. **33**X and **33**Y can be referred to as the specification of the anode **91**, the cathode **92** and the jelly electrolyte **93**, respectively, as illustrated in FIGS. **33**A-**33**U. The specification of the metal bumps or pillars **27** as shown in FIG. **33**Y can be referred to as the specification of the metal bumps or pillars **27** illustrated in FIGS. **25**G-**25**L and **33**N-**33**U. The process for forming the shielding ring **123** for containing the jelly electrolyte **93**, shown in FIGS. **33**X and **33**Y, can be referred to as that for forming the metal layer **4** and the bulk metal layer **9** as illustrated in FIGS. **33**A-**33**E. The element in FIGS. **33**X and **33**Y indicated by a same reference number as indicates the element in FIGS. **33**A-**33**U has a same material and spec as the element illustrated in FIGS. **33**A-**33**U.

[0951] After forming the structure shown in FIGS. **33**X and **33**Y, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0952] In the chip package, for example, the left one metal bump or pillar **27** can connect the metal trace **88***b* and the previously described inductor **36** of the semiconductor chip to a power bus or plane of a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. The right one metal bump or pillar **27** can connect the cathode **92** of the capacitor **87** and the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip to a ground bus or plane of the first external circuit through the bulk metal layer **9** in the through-silicon via **11***e* and through the fine-line metal trace **624**. A first metal bump **89** can connect the metal trace, bus or plane **81** of the semiconductor chip to a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output a regulated or converted power voltage Vcc to the second external circuit. Multiple second metal bumps **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the second external circuit.

[0953] Alternatively, in the chip package, a first metal bump **89** can connect the metal trace, bus or plane **81**P and the voltage regulator or converter circuit **41** of the semiconductor chip to a first external such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit. A second metal bump **89** can connect the metal trace, bus or plane **81** and of the semiconductor chip to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit. Multiple third metal bumps **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the first external circuit. The right one metal bump or pillar **27** can connect the cathode **92** of the capacitor **87** and the internal circuit **24** of the semiconductor chip to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, through the bulk metal layer **9** in the through-silicon via **11***e* and through the fine-line metal trace **624**.

[0954] FIGS. **34**A-**34**G show a process of forming a super capacitor **87***a*, a patterned circuit layer **801**, multiple metal bumps or pillars **89** and two polymer layers **98** and **99** at the active side of the thinned silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **33**T.

[0955] Referring to FIG. **34**A, after forming the structure shown in FIG. **33**T, the flux **32** is removed. Next, an adhesion/barrier/seed layer **8011** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** in the passivation layer **5**. The adhesion/barrier/seed layer **8011** can be formed by a suitable process or processes, e.g., by depositing an adhesion/barrier layer **8011***a* with a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then depositing a seed layer **8011***b* with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the adhesion/barrier layer **8011***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **8011***a* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **8011***b* may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[0956] For example, when the adhesion/barrier layer **8011***a* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a

thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** in the passivation layer **5**, the seed layer **8011***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the titanium-containing layer.

[0957] Alternatively, when the adhesion/barrier layer **8011***a* is formed by a suitable process or processes, e.g., by sputtering a composite layer including a titanium layer having a thickness between 0.01 and 0.15 micrometers on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** and a titanium-tungsten-alloy layer having a thickness between 0.1 and 0.35 micrometers on the titanium layer, the seed layer **8011***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the titanium-tungsten-alloy layer.

[0958] Alternatively, when the adhesion/barrier layer **8011***a* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** in the passivation layer **5**, the seed layer **8011***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the tantalum-containing layer.

[0959] Alternatively, when the adhesion/barrier layer **8011***a* is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.005 and 0.8 micrometers, and preferably between 0.05 and 0.5 micrometers, on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519**, **519'**, **521**, **522** and **524** in the passivation layer **5**, the seed layer **8011***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.005 and 0.5 micrometers, and preferably between 0.05 and 0.2 micrometers, on the chromium-containing layer.

[0960] After forming the adhesion/barrier/seed layer **8011**, an anode **91***a* and a cathode **92***a* can be formed on the seed layer **8011***b* of the adhesion/barrier/seed layer **8011**. The material of the anode **91***a* may include polyaniline, active carbon, graphite, polypyrrole, carbon nanotube, a NiCo alloy or RuO_2. Alternatively, the anode **91***a* may be a composite layer including a nickel layer on the seed layer **8011***b* and a carbon layer on a top surface and sidewall of the nickel layer. The material of the cathode **92***a* may include polyaniline, active carbon, graphite, carbon nanotube or polypyrrole. For example, when the anode **91***a* is a NiCo alloy, the cathode **92***a* may be active carbon or carbon nanotube. Alternatively, the anode **91***a* and the cathode **92***a* can be porous. The anode **91***a* has a thickness larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers, and has a width larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers. The cathode **92***a* has a thickness larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers, and has a width larger than 1 micrometer, such as between 1 and 20 micrometers, and preferably between 2 and 10 micrometers.

[0961] After forming the anode **91***a* and the cathode **92***a*, a photoresist layer **71**, such as positive-type photoresist layer or negative-type photoresist layer, having a thickness larger than 3 micrometers, such as between 3 and 110 micrometers, and preferably between 5 and 25 micrometers, is formed on the seed layer **8011***b*, on the anode **91***a* and on the cathode **92***a* by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **71** is patterned with the processes of exposure and development to form multiple openings **710** in the photoresist layer **71** exposing the seed layer **8011***b*.

[0962] Next, a bulk metal layer **8012** can be formed on the seed layer **8011***b*, exposed by the openings **710** in the photoresist layer **71**, of the adhesion/barrier/seed layer **8011** and in the openings **710** by a process including an electroplating process and/or an electroless plating process. The bulk metal layer **8012** may have a thickness larger than 2 micrometers, such as between 2 and 100 micrometers, and preferably between 3 and 20 micrometers, and larger than that of the seed layer **8011***b*, that of the adhesion/barrier layer **8011***a* and that of each of the fine-line metal layers **60**, respectively. The bulk metal layer **8012** may have a width larger than 1 micrometer, such as between 5 and 150 micrometers, and preferably between 5 and 50 micrometers, and larger than that of each of the fine-line metal layers **60**. The material of the bulk metal layer **8012** may include gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium, nickel or a composite of the previously described materials. The process of forming the bulk metal layer **8012** on the seed layer **8011***b*, exposed by the openings **710** in the photoresist layer **71**, of the adhesion/barrier/seed layer **8011** and in the openings **710** as shown in FIG. **34**A can be referred to as the process of forming the bulk metal layer **8012** on the seed layer, exposed by the openings **710** in the photoresist layer **71**, of the adhesion/barrier/seed layer **8011** and in the openings **710** as illustrated in FIG. **15**F. The specification of the bulk metal layer **8012** shown in FIG. **34**A can be referred to as the specification of the bulk metal layer **8012** illustrated in FIG. **15**F.

[0963] Referring to FIG. **34**B, after forming the bulk metal layer **8012**, the photoresist layer **71** is removed using an inorganic solution or using an organic solution with amide. Next, the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012**, the anode **91***a* and the cathode **92***a* is removed by etching the seed layer **8011***b* not under the bulk metal layer **8012**, the anode **91***a* and the cathode **92***a*, and then etching the adhesion/barrier layer **8011***a* not under the bulk metal layer **8012**, the anode **91***a* and the cathode **92***a*. The process of etching the seed layer **8011***b* of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012**,

the anode **91***a* and the cathode **92***a* as shown in FIG. **34**B can be referred to as the process of etching the seed layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** as illustrated in FIG. **15**H. The process of etching the adhesion/barrier layer **8011***a* of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012**, the anode **91***a* and the cathode **92***a* as shown in FIG. **34**B can be referred to as the process of etching the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** as illustrated in FIG. **15**H.

[0964] Accordingly, the anode **91***a* and the cathode **92***a* can be formed over the passivation layer **5** and at the active side of the thinned silicon substrate **1**, and the patterned circuit layer **801** composed of the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012** can be formed on the passivation layer **5** and at the active side of the thinned silicon substrate **1**. The patterned circuit layer **801** includes multiple metal traces **81**, **81**P and **82** on the passivation layer **5** and at the active side of the thinned silicon substrate **1**, and the metal traces **81**, **81**P and **82** are provided by the adhesion/barrier/seed layer **8011** and the bulk metal layer **8012**. The metal trace **81** can be connected to the voltage regulator or converter circuit **41** through the opening **519'** in the passivation layer **5** and through the fine-line metal trace **619'**, and to multiple power nodes of the internal circuit **21**, **22**, **23** and **24**. The metal trace **81**P can be connected to the voltage regulator or converter circuit **41** through the opening **519** in the passivation layer **5** and through the fine-line metal trace **619**. The metal trace **82** can be connected to the voltage regulator or converter circuit **41**, to a ground node of the internal circuit **21**, to a ground node of the internal circuit **22** through the opening **522** in the passivation layer **5** and through the fine-line metal trace **622**, to a ground node of the internal circuit **23** through the opening **522** in the passivation layer **5** and through the fine-line metal trace **622**, and to a ground node of the internal circuit **24** through the opening **524** in the passivation layer **5** and through the fine-line metal trace **624**. The metal traces **81**P and **82** can be optionally connected to the previously described ESD protection circuit **44**, which can be referred further to as FIG. **29**B.

[0965] Referring to FIG. **34**C, after the step illustrated in FIG. **34**B, a polymer layer **98** can be formed on the passivation layer **5** and on the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process. Multiple openings **980** in the polymer layer **98** are over multiple regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** and expose them. An opening **980***a* in the polymer layer **98** exposes the anode **91***a* and the cathode **92***a*, and the anode **91***a* and the cathode **92***a* are in the opening **980***a* and over the passivation layer **5**. The polymer layer **98** may have a thickness larger than 2 micrometers, such as between 2 and 30 micrometers, and larger than that of each of the fine-line dielectric layers **30**. The material of the polymer layer **98** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[0966] FIG. **34**D is a top view of FIG. **34**C. Referring to FIGS. **34**C and **34**D, the cathode **92***a* has multiple parallel lines **125***a* extending into gaps between multiple parallel lines **124***a* of the anode **91***a*. The horizontal space between the neighboring lines **124***a* and **125***a* of the cathode **92***a* and anode **91***a* can be larger than 0.1 micrometers, such as between 0.1 and 10 micrometers, and preferably between 1 and 5 micrometers. The anode **91***a* is connected to the node P of the voltage regulator or converter circuit **41** through the metal trace **81**. The cathode **92***a* is connected to the ground node Rs of the voltage regulator or converter circuit **41** and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the metal trace **82**.

[0967] After forming the polymer layer **98** and the openings **980** and **980***a* in the polymer layer **98**, a jelly electrolyte **93***a*, containing a polymer and metal ions, such as Li^+, Ni^+ or Cu^+, is formed in the opening **980***a* in the polymer layer **98**, on the passivation layer **5** exposed by the opening **980***a* and in the gaps between the parallel lines **124***a* and **125***a*, and covers top surfaces of the anode **91***a* and the cathode **92***a*.

[0968] After forming the jelly electrolyte **93***a*, the super capacitor **87***a* including the anode **91***a*, the cathode **92***a* and the jelly electrolyte **93***a* can be formed on the passivation layer **5** and in the opening **980***a* in the polymer layer **98**. The super capacitor **87***a* at the active side of the thinned silicon substrate **1** has capacitance in the range of between 0.01 and 100 microfarads, and has energy storage capability in the range of between 0.1 and 10 microfarads per square meter ($\mu F/mm^2$). The area of the super capacitor **87***a*, enclosed by the bold line shown in FIG. **34**D, is in the range of between 0.1 and 10 square meters. Alternatively, the jelly electrolyte **93***a* can be replaced by a liquid electrolyte containing a polymer and metal ions, such as Li^+, Ni^+ or Cu^+. The capacitor **87***a* is reversibly chargeable and dischargeable. The metal trace **81** can connect the anode **91***a* of the super capacitor **87***a* to the voltage regulator or converter circuit **41** and to the power nodes of the internal circuits **21**, **22**, **23** and **24**, and the metal trace **82** can connect the cathode **92***a* of the super capacitor **87***a* to the voltage regulator or converter circuit **41** and to the ground nodes of the internal circuits **21**, **22**, **23** and **24**.

[0969] Next, referring to FIG. **34**E, a polymer layer **99** is formed on the polymer layer **98** and covers the jelly electrolyte **93***a* of the super capacitor **87***a* by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and multiple openings **990** in the polymer layer **99** are over the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980** in the polymer layer **98** and expose them. The polymer layer **990** may have a thickness larger than 2 micrometers, such as between 2 and 30 micrometers, and larger than that of each of the fine-line dielectric layers **30**. The material of the polymer layer **99** may include benzocyclobutane (BCB), polyimide (P1), polybenzoxazole (PBO) or epoxy resin.

[0970] Next, referring to FIG. **34**F, a metal layer **89***a* can be formed on the polymer layer **99**, on the polymer layer **98** and on the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**. Next, a metal layer **89***b* can be formed on the metal layer **89***a*. The material of the metal layer **89***a* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the metal layer **89***b* may include

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copper, nickel, aluminum, gold, silver, platinum or palladium. The metal layers **89***a* and **89***b* may be formed by a suitable process or processes, e.g., by a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The metal layer **89***a* may have a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, and the metal layer **89***b* may have a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers.

[0971] For example, when the metal layer **89***a* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **99**, on the polymer layer **98** and on the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**, the metal layer **89***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the titanium-containing layer.

[0972] Alternatively, when the metal layer **89***a* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **99**, on the polymer layer **98** and on the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**, the metal layer **89***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the tantalum-containing layer.

[0973] Alternatively, when the metal layer **89***a* is formed by a suitable process or processes, e.g., by sputtering a chromium-containing layer, such as a single layer of chromium layer, having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, on the polymer layer **99**, on the polymer layer **98** and on the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**, the metal layer **89***b* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, between 0.08 and 0.15 micrometers, between 0.1 and 1 micrometers or between 0.2 and 0.5 micrometers, on the chromium-containing layer.

[0974] After forming the metal layer **89***b*, a photoresist layer **71***a* can be formed on the metal layer **89***b*, and multiple openings **71***b* in the photoresist layer **71***a* are over the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980** and expose the metal layer **89***b*. Next, a metal layer **89***c* can be formed on the metal layer **89***b* exposed by the openings **71***b* and in the openings **71***b* by a process including an electroplating process. The metal layer **89***c* may have a thickness larger than 3 micrometer, such as between 3 and 200 micrometers, and preferably between 5 and 100 micrometers, and larger than that of the metal layer **89***b*, that of the metal layer **89***a* and that of each of the fine-line metal layers **60**, respectively. The metal layer **89***c* may have a width larger than 1 micrometer, such as between 5 and 200 micrometers, and preferably between 5 and 50 micrometers, and larger than that of each of the fine-line metal layers **60**. The metal layer **89***c* may include copper, gold, nickel, aluminum, silver, platinum, solder or a composite of the previously described materials.

[0975] For example, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 3 micrometers, such as between 10 and 150 micrometers, and preferably between 20 and 100 micrometers, in the openings **71***b* and on the metal layer **89***b*, preferably the previously described copper layer **89***b*, exposed by the openings **71***b*.

[0976] Alternatively, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a gold layer, to a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **71***b* and on the metal layer **89***b*, preferably the previously described gold layer **89***b*, exposed by the openings **71***b*.

[0977] Alternatively, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a nickel layer, to a thickness larger than 3 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **71***b* and on the metal layer **89***b*, preferably the previously described copper layer or nickel layer **89***b*, exposed by the openings **71***b*.

[0978] Alternatively, the metal layer **89***c* can be composed of a single metal layer formed by a suitable process or processes, e.g., by electroplating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness larger than 5 micrometers, such as between 5 and 200 micrometers, and preferably between 10 and 150 micrometers, in the openings **71***b* and on the metal layer **89***b*, preferably the previously described copper layer or nickel layer **89***b*, exposed by the openings **71***b*.

[0979] Alternatively, the metal layer **89***c* can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 1 micrometer, such as between 3 and 150 micrometers, and preferably between 5 and 100 micrometers, in the openings **71***b* and on the metal layer **89***b*, preferably the previously described copper layer **89***b*, exposed by the openings **71***b*, next electroplating or electroless plating a nickel layer, to a thickness larger than 1 micrometer, such as between

1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **71***b* and on the electroplated copper layer in the openings **71***b*, and then electroplating or electroless plating a gold layer or a palladium layer, to a thickness larger than 0.005 micrometers, such as between 0.005 and 10 micrometers, and preferably between 0.05 and 1 micrometers, in the openings **71***b* and on the electroplated or electroless plated nickel layer in the openings **71***b*.

[0980] Alternatively, the metal layer **89***c* can be composed of triple metal layers formed by a suitable process or processes, e.g., by electroplating a copper layer, to a thickness larger than 1 micrometer, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, in the openings **71***b* and on the metal layer **89***b*, preferably the previously described copper layer **89***b*, exposed by the openings **71***b*, next electroplating or electroless plating a nickel layer, to a thickness larger than 1 micrometer, such as between 1 and 15 micrometers, and preferably between 2 and 10 micrometers, in the openings **71***b* and on the electroplated copper layer in the openings **71***b*, and then electroplating or electroless plating a solder layer, such as a bismuth-containing layer, an indium-containing layer or a tin-containing layer of a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, to a thickness larger than 1 micrometer, such as between 5 and 100 micrometers, and preferably between 10 and 50 micrometers, in the openings **71***b* and on the electroplated or electroless plated nickel layer in the openings **71***b*.

[0981] Referring to FIG. **34**G, after forming the metal layer **89***c* as illustrated in FIG. **34**F, the photoresist layer **71***a* is removed using an inorganic solution or using an organic solution with amide. Next, the metal layer **89***b* not under the metal layer **89***c* is removed by an etching process, and then the metal layer **89***a* not under the metal layer **89***c* is removed by an etching process. The process of removing the metal layer **89***b* not under the metal layer **89***c* as shown in FIG. **34**G can be referred to as the process of removing the seed layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** as illustrated in FIG. **15**H. The process of removing the metal layer **89***a* not under the metal layer **89***c* as shown in FIG. **34**G can be referred to as the process of etching the adhesion/barrier layer of the adhesion/barrier/seed layer **8011** not under the bulk metal layer **8012** as illustrated in FIG. **15**H.

[0982] Accordingly, the metal bumps or pillars **89** provided by the metal layers **89***a*, **89***b* and **89***c* can be formed on the polymer layers **98** and **99** and on the regions of the topmost layer of gold, copper, silver, aluminum, palladium, platinum, rhodium, ruthenium, rhenium or nickel of the previously described various the bulk metal layer **8012** exposed by the openings **980**. The metal layer **89***c* of the metal bumps or pillars **89** can be used to be connected to an external circuit, such as ball-grid-array (BGA) substrate, printed circuit board, semiconductor chip, metal substrate, glass substrate or ceramic substrate, by bonding the metal layer **89***c* with the external circuit.

[0983] In FIG. **34**G, a bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**, and includes the insulating layer **3**, the capacitor **87** composed of the anode **91**, the cathode **92** and the jelly electrolyte **93**, the metal traces **88***a*, **88***b* and **88***c*, and the polymer layers **14** and **133**, and the openings **14***a*, **14***c* and **14***d* in the polymer layer **14** are under the bulk metal layer **9**, the opening **14***b* in the polymer layer **14** is under the insulating layer **3**, and the openings **133***a* in the polymer layer **133** are under the bulk metal layer **9**. An over-passivation scheme **102** is formed with the metal traces **81**, **81**P and **82** provided by the patterned circuit layer **801**, the capacitor **87***a* composed of the anode **91***a*, the cathode **92***a* and the jelly electrolyte **93***a*, the polymer layers **98** and **99**, and the metal bumps **89**, at the active side of the thinned silicon substrate **1**, and the openings **980** in the polymer layer **98** are over the patterned circuit layer **801**, the opening **980***a* in the polymer layer is over the passivation layer **5**, and the openings **990** in the polymer layer **99** are over the patterned circuit layer **801**.

[0984] After the step illustrated in FIG. **34**G, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0985] In the chip package, for example, one of the metal bumps or pillars **27** can connect the metal trace **88***b* of the semiconductor chip to a first external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***b*, through the bulk metal layer **9** in the through-silicon via **11***a* and through the fine-line metal trace **619**. Another one of the metal bumps or pillars **27** can connect the metal trace **88***c* of the semiconductor chip to the first external circuit to output a regulated or converted power voltage Vcc to the first external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'** and to the anode **91** of the capacitor **87** through the metal trace **88***c*. The other one of the metal bumps or pillars **27** can connect the metal trace **88***a* and the capacitor **87** of the semiconductor chip to a ground bus or plane of the first external circuit, and can be connected to the cathode **92** of the capacitor **87** and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. One of the metal bumps or pillars **89** can connect the metal trace **81** of the semiconductor chip to a second external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to output the regulated or converted power voltage Vcc to the second external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **81** and the fine-line metal trace **619'** and to the anode **91***a* of the capacitor **87***a* and the power node Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24** through the metal trace **81**. The other one of the metal bumps or pillars **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the second external circuit, and can be connected to the cathode **92***a* of the capacitor **87***a* and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the metal trace **82**.

[0986] Alternatively, in the chip package, one of the metal bumps or pillars **89** can connect the metal trace **81**P of the semiconductor chip to a first external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the first external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **81**P and the fine-line metal trace **619**. Another one of the metal bumps or pillars **89** can connect the metal trace **81** of the semiconductor chip to the first external circuit to output a regulated or con-

verted power voltage Vcc to the first external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **81** and the fine-line metal trace **619'** and to the anode **91***a* of the capacitor **87***a* and the power node Tp, Up, Vp and Wp of the internal circuits **21**, **22**, **23** and **24** through the metal trace **81**. The other one of the metal bumps or pillars **89** can connect the ground plane, bus or trace **82** of the semiconductor chip to a ground bus or plane of the first external circuit, and can be connected to the cathode **92***a* of the capacitor **87***a* and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the metal trace **82**. One of the metal bumps or pillars **27** can connect the metal trace **88***a* and the capacitor **87** of the semiconductor chip to a ground bus or plane of a second external circuit, such as semiconductor chip, printed circuit board, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, and can be connected to the cathode **92** of the capacitor **87** and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** through the metal trace **88***a*. The other one of the metal bumps or pillars **27** can connect the metal trace **88***c* of the semiconductor chip to the second external circuit to output the regulated or converted power voltage Vcc to the second external circuit, and can be connected to the voltage regulator or converter circuit **41** through the metal trace **88***c* and the fine-line metal trace **619'** and to the anode **91** of the capacitor **87** through the metal trace **88***c*.

[0987] However, the previously described inductor **36** and the previously described capacitor **87** can be discrete devices. In the following, a process shown in FIGS. **35**A-**35**D is introduced for connecting a discrete inductor **36** and a discrete capacitor **87** to a semiconductor wafer **10**. The discrete inductor **36** can be used for the inductor **36** shown in FIGS. **29**A and **29**B, and the discrete capacitor **87** can be used for the capacitor **87** shown in FIGS. **29**A, **29**B and **29**D.

[0988] Referring to FIG. **35**A, the silicon substrate **1** of the semiconductor wafer **10** illustrated in FIG. **30**A is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) the backside **1***a* of the silicon substrate **1**. Next, the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* can be formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing the regions **60***a* of the fine-line metal layers **60**, and then the insulating layer **3** can be formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, which can be referred to as the steps illustrated in FIGS. **24**C-**24**H or FIGS. **24**I-**24**N. The through-silicon vias **11***a*, **11***d*, **11***e* and **11***f* penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. Next, the interconnecting structures **88** provided by the metal layers **4** and **9** can be formed in the through-silicon vias **11***a*, **11***d*, **11***e* and **11***f*, on the insulating layer **3** and at the backside **1***a* of the thinned silicon substrate **1**, which can be referred to as the steps illustrated in FIGS. **25**A-**25**F. The interconnecting structures **88** include multiple metal traces **88***a*, **88***b* and **88***c*.

[0989] Referring to FIG. **35**B, after the step illustrated in FIG. **35**A, a polymer layer **14** is formed on the insulating layer **3** and on the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** by a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process, and multiple openings **14***a* in the polymer layer **14** are over multiple regions of the topmost layer of copper, gold, aluminum, nickel or palladium of the previously described various bulk metal layer **9** and expose them. The polymer layer **14** may have a thickness larger than 3 micrometers, such as between 3 and 50 micrometers, and preferably between 5 and 25 micrometers. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin. The process of forming the polymer layer **14** and the openings **14***a* in the polymer layer **14** as shown in FIG. **35**B can be referred to as the process of forming the polymer layer **14** and the opening **14***a* in the polymer layer **14** as illustrated in FIGS. **25**G.

[0990] Referring to FIG. **35**C, after the step illustrated in FIG. **35**B, using the steps illustrated in FIGS. **15**D-**15**H, multiple patterned circuit layers **812** composed of an adhesion/barrier/seed layer **8121** and a metal layer **8122** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **519** and **519'**, and a patterned circuit layer **821** composed of an adhesion/barrier/seed layer **8211** and a metal layer **8212** can be formed on the passivation layer **5** and on the regions **600***a* of the metal traces or pads **600** exposed by the openings **521**, **522** and **524**. Next, a polymer layer **98** is formed on the metal layer **8122** of the patterned circuit layers **812**, on the metal layer **8212** of the patterned circuit layer **821** and on the passivation layer **5**, and multiple openings **980** in the polymer layer **98** are over multiple contact points of the metal layers **8122** and **8212** and expose them, which can be referred to as the step illustrated in FIG. **15**I. Next, multiple metal bumps **89** provided by triple metal layers **89***a*, **89***b* and **89***c* are formed on the polymer layer **98** and on the contact points of the metal layers **8122** and **8212** exposed by the openings **980**, which can be referred to as the step illustrated in FIG. **30**L. Alternatively, the steps of forming the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89** can be performed before the steps illustrated in FIGS. **35**A and **35**B. The specification of the metal bumps **89** shown in FIG. **35**C can be referred to as the specification of the metal bumps **89** as illustrated in FIG. **30**L. Accordingly, the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89** can be formed over the passivation layer **5** at the active side of the thinned silicon substrate **1**.

[0991] Referring to FIG. **35**D, the discrete inductor **36** and the discrete capacitor **87** can be connected to the bulk metal layer **9** exposed by the openings **14***a* through multiple metal bumps **144**, such as solder balls or bumps, gold bumps, copper bumps, silver bumps, aluminum bumps or nickel bumps, having a thickness larger than 1 micrometer, such as between 10 and 250 micrometers. Accordingly, a bottom scheme **103** at the backside **1***a* of the thinned silicon substrate **1** is formed with the insulating layer **3**, the metal traces **88***a*, **88***b* and **88***c* provided by the metal layers **4** and **9**, the discrete inductor **36**, the discrete capacitor **87**, the metal bumps **144**, and the polymer layer **14**, and the openings **14***a* in the polymer layer **14** are over the bulk metal layer **9**. An over-passivation scheme **102** is formed with the patterned circuit layers **812** and **821**, the polymer layer **98** and the metal bumps **89**, at the active side of the thinned silicon substrate **1**, and the openings **980** in the polymer layer **98** are under the patterned circuit layers **812** and **821**. After forming the structure shown in FIG. **35**D, the semiconductor wafer **10** can be cut into a plurality of individual semiconductor chip by a die-sawing process. After the die-sawing process, the semiconductor chip cut from the semiconductor wafer **10** can be packaged for a chip package.

[0992] In the chip package, the discrete inductor **36** at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor chip can be connected to the voltage regulator or converter circuit **41** of the semiconductor chip through the metal traces **88***b* and **88***c*, through the bulk metal layer **9** in the through-silicon vias **11***f* and **11***a* and through the fine-line metal traces **619** and **619'**. The discrete capacitor **87** at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor chip can be connected to the voltage regulator or converter circuit **41** of the semiconductor chip through the metal trace **88***c*, through the bulk metal layer **9** in the through-silicon via **11***f* and through the fine-line metal trace **619'**, to the discrete inductor **36** through the metal trace **88***c*, to the internal circuit **21** through the metal trace **88***a* and through the fine-line metal trace **621**, to the internal circuits **22** and **23** through the metal trace **88***a*, through the bulk metal layer **9** in the through-silicon via **11***d* and through the fine-line metal trace **622**, and to the internal circuit **24** through the metal trace **88***a*, through the bulk metal layer **9** in the through-silicon via **11***e* and through the fine-line metal trace **624**. One of the metal bumps **89** can connect the metal trace **81**P at the active side of the thinned silicon substrate **1** of the semiconductor chip to an external circuit, such as printed circuit board, semiconductor chip, ball-grid-array (BGA) substrate, metal substrate, glass substrate or ceramic substrate, to receive an external power voltage Vdd from the external circuit, and can be connected to the metal trace **88***b* and the discrete inductor **36** at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor chip and the voltage regulator or converter circuit **41** of the semiconductor chip through the metal trace **81**P at the active side of the thinned silicon substrate **1** of the semiconductor chip and through the fine-line metal trace **619** of the semiconductor chip. Another one of the metal bumps **89** can connect the metal trace **81** at the active side of the thinned silicon substrate **1** of the semiconductor chip to the external circuit to output a regulated or converted power voltage Vcc to the external circuit, and can be connected to the metal trace **88***c* and the discrete inductor **36** at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor chip and the voltage regulator or converter circuit **41** of the semiconductor chip through the metal trace **81** at the active side of the thinned silicon substrate **1** of the semiconductor chip and through the fine-line metal trace **619'** of the semiconductor chip. The other two of the metal bumps **89** can connect the ground plane, bus or trace **82** at the active side of the thinned silicon substrate **1** of the semiconductor chip to a ground bus or plane of the external circuit, and can be connected to the metal trace **88***a* at the backside **1***a* of the thinned silicon substrate **1** of the semiconductor chip and the ground nodes Ts, Us, Vs and Ws of the internal circuits **21**, **22**, **23** and **24** of the semiconductor chip through the ground plane, bus or trace **82** at the active side of the thinned silicon substrate **1**.

[0993] Referring to FIG. **36**A, a chip-package module **118** contains a ball-grid-array (BGA) substrate **110**, two chip packages **57** and **84** on the top side of the BGA substrate **110**, a discrete capacitor **112** over the top side of the BGA substrate **110**, and multiple solder balls **111***a* on the bottom side of the BGA substrate **110**. The discrete capacitor **112** can be provided on and connected to the BGA substrate **110** through multiple solder balls **111***d*. The BGA substrate **110** of the chip-package module **118** can be provided on and connected to a substrate, such as printed circuit board, metal substrate, glass substrate or ceramic substrate, through the solder balls **111***a*. The solder balls **111***a* and **111***d* may include bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy.

[0994] The chip package **84** contains a ball-grid-array (BGA) substrate **113**, two dynamic-random-access-memory (DRAM) chips **104** over the top side of the BGA substrate **113**, two flash memory chips **114** over the DRAM chips **104** and over the BGA substrate **113**, an application-specific-integrated-circuit (ASIC) chip **115** on the top one of the flash memory chips **114**, over the DRAM chips **104** and over the BGA substrate **113**, multiple solder balls **111***c* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on the bottom side of the BGA substrate **113**, multiple wirebonded wires **119**, such as gold wires, copper wires or aluminum wires, connecting one of the chips **104**, **114** and **115** to the other one of the chips **104**, **114** and **115** or to the BGA substrate **113**, and a molding compound **116**, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **113**, on the wirebonded wires **119** and on the chips **104**, **114** and **115**, encapsulating the chips **104**, **114** and **115** and the wirebonded wires **119**. The BGA substrate **113** of the chip package **84** can be provided on and connected to the BGA substrate **110** through the solder balls **111***c*.

[0995] The line **5** shown in FIG. **36**A indicates the previously described passivation layer. The DRAM chips **104** and the flash memory chips **114** each contain a combination of the previously described silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5** and the previously described over-passivation scheme **102**, and the combination can be referred to one of FIGS. **1**B-**1**D, **3**B-**3**D, **5**B, **5**K, **5**S, **5**U-**5**Z, **7**B-**7**D, **8**A-**8**F, **10**A-**10**I, **12**B-**12**D, **14**B-**14**D, **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H, **20** and **23**K, and, as shown in these figures, the IC structure **6***a* that is over the silicon substrate **1** and under the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuits **43** and **44**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. Regarding the chips **104** and **114**, the patterned circuit layer of the over-passivation scheme **102** can be connect to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[0996] The bottom one of the DRAM chips **104** can be mounted onto the BGA substrate **113** by adhering the silicon substrate **1** of the bottom one of the DRAM chips **104** to the top side of the BGA substrate **113** using a film **135** of a glue material, such as a polymer or an epoxy-based material, with a thickness between 1 and 50 micrometers. The top one of the DRAM chips **104** can be mounted onto the bottom one of the DRAM chips **104** by adhering the silicon substrate **1** of the top one of the DRAM chips **104** to the over-passivation scheme **102** of the bottom one of the DRAM chips **104** using another film **135** of the glue material. The bottom one of the flash memory chips **114** can be mounted onto the top one of the DRAM chips **104** by adhering the silicon substrate **1** of the bottom one of the flash memory chips **114** to the over-passivation scheme **102** of the top one of the DRAM chips **104** using another film **135** of the glue material. The top one of the flash memory chips **114** can be mounted onto the bottom one of the flash memory chips **114** by adhering the silicon sub-

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strate **1** of the top one of the flash memory chips **114** to the over-passivation scheme **102** of the bottom one of the flash memory chips **114** using another film **135** of the glue material. The ASIC chip **115** can be mounted onto the top one of the flash memory chips **114** by adhering the ASIC chip **115** to the over-passivation scheme **102** of the top one of the flash memory chips **114** using another film **135** of the glue material.

[0997] The top one of the DRAM chips **104** has a right portion overhanging the bottom one of the DRAM chips **104**, and the bottom one of the DRAM chips **104** has a left portion not vertically under the top one of the DRAM chips **104**. The top one of the DRAM chips **104** has a left sidewall recessed from that of the bottom one of the DRAM chips **104**. The bottom one of the flash memory chips **114** has a right portion overhanging the top one of the DRAM chips **104**, and the top one of the DRAM chips **104** has a left portion not vertically under the bottom one of the flash memory chips **114**. The bottom one of the flash memory chips **114** has a left sidewall recessed from that of the top one of the DRAM chips **104**. The top one of the flash memory chips **114** has a right portion overhanging the bottom one of the flash memory chips **114**, and the bottom one of the flash memory chips **114** has a left portion not vertically under the top one of the flash memory chips **114**. The top one of the flash memory chips **114** has a left sidewall recessed from that of the bottom one of the flash memory chips **114**.

[0998] One of the wirebonded wires **119**, for example, can be bonded on the bulk metal layer **8012** of the patterned circuit layer **801** in the over-passivation scheme **102**, on the bulk metal layer **8022** of the patterned circuit layer **802** in the over-passivation scheme **102**, on the bulk metal layer **8032** of the patterned circuit layer **803** in the over-passivation scheme **102**, on the metal trace **81** in the over-passivation scheme **102**, on the metal trace **81**P in the over-passivation scheme **102**, on the metal trace **82** in the over-passivation scheme **102**, on the metal trace **83** in the over-passivation scheme **102**, on the metal trace **83'** in the over-passivation scheme **102**, on the metal trace **83***r* in the over-passivation scheme **102**, or on the metal trace **85** in the over-passivation scheme **102**, to connect one of the chips **104** and **114** to the other one of the chips **104** and **114**, to the chip **115** or to the BGA substrate **113**.

[0999] The chip package **57** contains a ball-grid-array (BGA) substrate **117**, a chip **101** on the top side of the BGA substrate **117**, a memory chip **100**, such as dynamic-random-access-memory (DRAM) chip or statistic-random-access-memory (SRAM) chip, over the chip **101** and over the BGA substrate **117**, multiple solder balls **111***b* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on the bottom side of the BGA substrate **117**, a super discrete capacitor **94** over the chip. **101** and over the BGA substrate **117**, a super discrete inductor **95** over the chip **101** and over the BGA substrate **117**, multiple wirebonded wires **119***a*, such as gold wires, copper wires or aluminum wires, connecting the chip **101** to the BGA substrate **117**, and a molding compound **120**, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **117**, on the wirebonded wires **119***a*, on the chips **100** and **101**, on the super discrete capacitor **94** and on the super discrete inductor **95**, encapsulating the chips **100** and **101**, the wirebonded wires **119***a*, the super discrete capacitor **94** and the super discrete inductor **95**. The BGA substrate **117** of the chip package **57** can be provided on and connected to the BGA substrate **110** through the solder balls **111***b*.

[1000] The chip **101** can be a central-processing-unit (CPU) chip designed by x86 architecture, a central-processing-unit (CPU) chip designed by non x86 architectures, such as ARM, Strong ARM or MIPs, a baseband chip, a graphics-processing-unit (GPU) chip, a digital-signal-processing (DSP) chip, a global-positioning-system (GPS) chip, a bluetooth chip, a wireless local area network (WLAN) chip, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any baseband circuit block, a system-on chip (SOC) including a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any graphics-processing-unit (GPU) circuit block, a system-on chip (SOC) including a baseband circuit block, a graphics-processing-unit (GPU) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any wireless local area network (WLAN) circuit block, a system-on chip (SOC) including a baseband circuit block and a wireless local area network (WLAN) circuit block, but not including any graphics-processing-unit (GPU) circuit block and any central-processing-unit (CPU) circuit block, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block and a wireless local area network (WLAN) circuit block, but not including any baseband circuit block and any central-processing-unit (CPU) circuit block, or a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures. Alternatively, the chip **101** can be a chip including a central-processing-unit (CPU) circuit block, a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a bluetooth circuit block, a global-positioning-system (GPS) circuit block, and/or a wireless local area network (WLAN) circuit block. The chip **101**, graphics-processing-unit (GPU) chip, or the graphics-processing-unit (GPU) circuit block in the chip **101** can be designed for 2D or 3D video display, and can be connected to a 3D video display, such as 3D television (3D TV), or a 3D video game player through the wirebonded wires **119***a*, the BGA substrates **117** and **110** and the solder balls **111***a* and **111***b*.

[1001] The chip **101** contains a combination of the previously described silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5** and the previously described over-passivation scheme **102**, and the combination can be referred to one of FIGS. **1**B-**1**D, **3**B-**3**D, **5**B, **5**K, **5**S, **5**U-**5**Z, **7**B-**7**D, **8**A-**8**F, **10**A-**10**I, **12**B-**12**D, **14**B-**14**D, **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H, **20** and **23**K, and, as shown in these figures, the IC structure **6***a* that is over the silicon substrate **1** and under the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuits **43** and **44**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**,

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and etc. Regarding the chip **101**, the patterned circuit layer of the over-passivation scheme **102** can be connect to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1002] The super discrete capacitor **94** and the super discrete inductor **95** can be provided on and connected to the previously described patterned circuit layer of the over-passivation scheme **102** of the chip **101** through multiple solder balls **111***e* including bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. For example, the process for mounting the discrete capacitor **94** and the discrete inductor **95** on the over-passivation scheme **102** of the chip **101** may be performed by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points, optionally exposed by openings in the topmost polymer layer, of the patterned circuit layer **801**, **802** or **803** or the metal trace **81**, **81**P, **82**, **83**, **83'**, **83***r* or **85** in the over-passivation scheme **102** of the chip **101**, then mounting the discrete capacitor **94** and the discrete inductor **95** onto the solder paste, and then reflowing or heating the solder paste to form the solid solder balls **111***e* bonding the discrete capacitor **94** and the discrete inductor **95** to the chip **101**.

[1003] The chip **101** can be mounted onto the BGA substrate **117** by adhering the silicon substrate **1** of the chip **101** to the top side of the BGA substrate **117** using another film **135** of the glue material. The memory chip **100** can be provided on and connected to the patterned circuit layer in the over-passivation scheme **102** of the chip **101** through multiple metal balls, bumps or posts **132**, such as copper bumps or posts, solder balls or bumps, nickel bumps or posts or gold bumps or posts, with a thickness larger than 5 micrometers, such as between 10 and 100 micrometers or between 50 and 200 micrometers, and the pitch between the neighboring metal balls, bumps or posts **132** can be larger than 10 micrometers, such as between 10 and 100 micrometers. An underfill **107**, such as a polymer, is filled into the gap between the chip **101** and the memory chip **100**, and encloses the metal balls, bumps or posts **132**.

[1004] For the process to mounting the memory chip **100** onto the chip **101**, the metal balls, bumps or posts **132** can be originally formed on the memory chip **100**, and then the metal balls, bumps or posts **132** can be bonded with multiple contact points, optionally exposed by openings in the topmost polymer layer, of the patterned circuit layer **801**, **802** or **803** or the metal trace **81**, **81**P, **82**, **83**, **83'**, **83***r* or **85** in the over-passivation scheme **102** of the chip **101**. For example, the process for mounting the memory chip **100** onto the chip **101** may be performed by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on the contact points, optionally exposed by openings in the topmost polymer layer, of the patterned circuit layer **801**, **802** or **803** or the metal trace **81**, **81**P, **82**, **83**, **83'**, **83***r* or **85** in the over-passivation scheme **102** of the chip **101**, then mounting the metal balls, bumps or posts **132** preformed on the memory chip **100** onto the solder paste, and then reflowing or heating the solder paste to form a solid solder bonding the metal balls, bumps or posts **132** to the chip **101**. Alternatively, the metal balls, bumps or posts **132** can be originally provided by the previously described metal bumps **89** of the over-passivation scheme **102** of the chip **101**, as shown in FIGS. **8**A-**8**F, **10**A-**10**E, **15**L, **15**M, **16**M and **20**, and then the metal balls, bumps or posts **132** can be bonded with the memory chip **100**.

[1005] One of the wirebonded wires **119***a*, for example, can be bonded on the bulk metal layer **8012** of the patterned circuit layer **801** in the over-passivation scheme **102**, on the bulk metal layer **8022** of the patterned circuit layer **802** in the over-passivation scheme **102**, on the bulk metal layer **8032** of the patterned circuit layer **803** in the over-passivation scheme **102**, on the metal trace **81** in the over-passivation scheme **102**, on the metal trace **81**P in the over-passivation scheme **102**, on the metal trace **82** in the over-passivation scheme **102**, on the metal trace **83** in the over-passivation scheme **102**, on the metal trace **83'** in the over-passivation scheme **102**, on the metal trace **83***r* in the over-passivation scheme **102**, or on the metal trace **85** in the over-passivation scheme **102**, to connect the chip **101** to the BGA substrate **117**.

[1006] For low power consumption design, a wide-bit and small driver interface circuit **109** can be provided between the memory chip **100** and the chip **101**. The chip **101** has multiple input/output (I/O) pads connected to the memory chip **100**, and each of the I/O pads is connected to no ESD protection circuit or a smaller ESD protection circuit and a driver or receiver in the chip **101**, and the driver has output capacitance between 0.01 and 10 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF, and the receiver has input capacitance between 0.01 and 20 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF. The memory chip **100** has multiple I/O pads connected to the chip **101**, and each of the I/O pads is connected to no ESD protection circuit or a smaller ESD protection circuit, and a driver or receiver in the memory chip **100**, and the driver has output capacitance between 0.01 and 10 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF, and the receiver has input capacitance between 0.01 and 20 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF. The data width between the chip **101** and the memory chip **100** can be larger than 2^7, such as 2^7, 2^8, 2^9, 2^{10} or 2^{11}.

[1007] Furthermore, for low power consumption design, there can be provided with a green power supply circuit **108**, such as regulator, with the super discrete capacitor **94** and the super discrete inductor **95** provided on the chip **101** using the solder balls **111***e*.

[1008] The chip package **57**, for example, can be formed by a suitable process or processes, e.g., by bonding the metal balls, bumps or posts **132** originally formed on a plurality of the memory chip **100** onto multiple contact points, optionally exposed by openings in the topmost polymer layer, of the patterned circuit layer **801**, **802** or **803** in the over-passivation scheme **102** of the wafer **10** finalized to be cut into a plurality of the chip **101**, for example, shown in FIG. **15**H, **15**K, **16**L, **17**J, **18**I or **19**H, next flowing the underfill **107** into gaps between the wafer **10** and the plurality of the memory chip **100**, enclosing the metal balls, bumps or posts **132**, next bonding a plurality of the discrete capacitor **94** and a plurality of the discrete inductor **95** onto the contact points, optionally exposed by the openings in the topmost polymer layer, of the

patterned circuit layer **801**, **802** or **803** in the over-passivation scheme **102** of the wafer **10**, for example, shown in FIG. **15**H, **15**K, **16**L, **17**J, **18**I or **19**H through the solder balls **111***e* using a surface-mount technology (SMT), next cutting the wafer **10** to singularize a plurality of stacked unit including the chips **100** and **101**, the discrete capacitor **94** and the discrete inductor **95**, next mounting the stacked unit onto the top side of the BGA substrate **117** by adhering the chip **101** to the top side of the BGA substrate **117** using the film **135** of the glue material, next bonding the wires **119***a* to the chip **101** and to the BGA substrate **117** by a wirebonding process, next forming the molding compound **120** on the top side of the BGA substrate **117**, on the wires **119***a*, on the chips **100** and **101**, on the discrete capacitor **94** and on the discrete inductor **95**, encapsulating the chips **100** and **101**, the wires **119***a*, the discrete capacitor **94** and the discrete inductor **95**, and then forming the solder balls **111***b* on the bottom side of the BGA substrate **117** by a ball planting process.

[1009] Referring to FIG. **36**B, a chip-package module **118***a* contains a ball-grid-array (BGA) substrate **110**, a chip package **57***a* on the top side of the BGA substrate **110**, the chip package **84** illustrated in FIG. **36**A on the top side of the BGA substrate **110**, a discrete capacitor **112** over the top side of the BGA substrate **110**, and multiple solder balls **111***a* on the bottom side of the BGA substrate **110**. The discrete capacitor **112** can be provided on and connected to the BGA substrate **110** through multiple solder balls **111***d*. The BGA substrate **110** of the chip-package module **118***a* can be provided on and connected to a substrate, such as printed circuit board, metal substrate, glass substrate or ceramic substrate, through the solder balls **111***a*. The solder balls **111***a* and **111***d* may include bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The specification of the chip package **84** illustrated in FIG. **36**B can be referred to as the specification of the chip package **84** as illustrated in FIG. **36**A, and the process of forming the chip package **84** as shown in FIG. **36**B can be referred to as the process of forming the chip package **84** as illustrated in FIG. **36**A. The line **5** shown in FIG. **36**B indicates the previously described passivation layer, and the line **1***a* shown in FIG. **36**B indicates the previously described backside of the thinned silicon substrate **1**.

[1010] The chip package **57***a* contains a ball-grid-array (BGA) substrate **117**, a chip **101***a* on the top side of the BGA substrate **117**, a memory chip **100**, such as dynamic-random-access-memory (DRAM) chip or statistic-random-access-memory (SRAM) chip, over the chip **101***a* and over the BGA substrate **117**, multiple solder balls **111***b* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on the bottom side of the BGA substrate **117**, a super discrete capacitor **94** over the chip **101***a* and over the BGA substrate **117**, a super discrete inductor **95** over the chip **101***a* and over the BGA substrate **117**, and a molding compound **120**, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **117**, on the chips **100** and **101***a*, on the discrete capacitor **94** and on the discrete inductor **95**, encapsulating the chips **100** and **101***a* the discrete capacitor **94** and the discrete inductor **95**. The BGA substrate **117** of the chip package **57***a* can be provided on and connected to the BGA substrate **110** through the solder balls **111***b*.

[1011] The chip **101***a* can be a central-processing-unit (CPU) chip designed by x86 architecture, a central-processing-unit (CPU) chip designed by non x86 architectures, such as ARM, Strong ARM or MIPs, a baseband chip, a graphics-processing-unit (GPU) chip, a digital-signal-processing (DSP) chip, a global-positioning-system (GPS) chip, a bluetooth chip, a wireless local area network (WLAN) chip, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any baseband circuit block, a system-on chip (SOC) including a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any graphics-processing-unit (GPU) circuit block, a system-on chip (SOC) including a baseband circuit block, a graphics-processing-unit (GPU) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any wireless local area network (WLAN) circuit block, a system-on chip (SOC) including a baseband circuit block and a wireless local area network (WLAN) circuit block, but not including any graphics-processing-unit (GPU) circuit block and any central-processing-unit (CPU) circuit block, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block and a wireless local area network (WLAN) circuit block, but not including any baseband circuit block and any central-processing-unit (CPU) circuit block, or a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures. Alternatively, the chip **101***a* can be a chip including a central-processing-unit (CPU) circuit block, a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a bluetooth circuit block, a global-positioning-system (GPS) circuit block, and/or a wireless local area network (WLAN) circuit block. The chip **101***a*, graphics-processing-unit (GPU) chip, or the graphics-processing-unit (GPU) circuit block in the chip **101***a* can be designed for 2D or 3D video display, and can be connected to a 3D video display, such as 3D television (3D TV), or a 3D video game player through the BGA substrates **117** and **110** and the solder balls **111***a* and **111***b*.

[1012] The chip **101***a* contains a combination of the previously described thinned silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5**, the previously described over-passivation scheme **102**, multiple through-silicon vias **11** and the previously described bottom scheme **103** including the metal bumps or pillars **27**, and the combination can be referred to one of FIGS. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, and, as shown in these figures, the IC structure **6***a* between the thinned silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuit **43**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. In FIG. **36**B, regarding the chip **101***a*, the over-passivation scheme **102** is formed on the passivation layer **5** at the active side of the thinned silicon substrate **1**, and the bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**. Regarding the chip **101***a*, the through-silicon vias

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11 providing for the previously described vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and/or **11***f* in FIG. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y or **34**G are formed in the thinned silicon substrate **1**, and the specification of the through-silicon vias **11** illustrated in FIG. **36**B can be referred to as the specification of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N, and the process of forming the through-silicon vias **11** as shown in FIG. **36**B can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N. Regarding the chip **101***a*, the metal layer of the bottom scheme **103** can be connected to the fine-line scheme **6** of the IC structure **6***a* through the bulk metal layer **9** in the through-silicon vias **11** and to the BGA substrate **117** through the metal bumps or pillars **27**, and the patterned circuit layer of the over-passivation scheme **102** can be connected to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1013] The chip **101***a* can be provided on and connected to the BGA substrate **117** through the metal bumps or pillars **27** of the bottom scheme **103** of the chip **101***a*. An underfill **107***a*, such as a polymer, is filled into the gap between the chip **101***a* and the top side of the BGA substrate **117**, and encloses the metal bumps or pillars **27**. The super discrete capacitor **94** and the super discrete inductor **95** can be connected to the previously described patterned circuit layer in the over-passivation scheme **102** of the chip **101***a* through multiple solder balls **111***e* including bismuth, indium, a tin-silver alloy, a tin-silver-copper alloy or a tin-lead alloy. The memory chip **100** can be connected to the patterned circuit layer in the over-passivation scheme **102** of the chip **101***a* through multiple metal balls, bumps or posts **132**, such as copper bumps or posts, solder balls or bumps, nickel bumps or posts or gold bumps or posts, with a thickness larger than 5 micrometers, such as between 10 and 100 micrometers or between 50 and 200 micrometers, and the pitch between the neighboring metal balls, bumps or posts **132** can be larger than 10 micrometers, such as between 10 and 100 micrometers. The metal balls, bumps or posts **132** can be originally formed on the memory chip **100**, and then the metal balls, bumps or posts **132** can be bonded with the chip **101***a*. Alternatively, the metal balls, bumps or posts **132** can be originally provided by the previously described metal bumps **89** of the over-passivation scheme **102** of the chip **101***a*, as shown in FIGS. **25**T, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, and then the metal balls, bumps or posts **132** can be bonded with the memory chip **100**. An underfill **107**, such as a polymer, is filled into the gap between the chip **101***a* and the memory chip **100**, and encloses the metal balls, bumps or posts **132**.

[1014] For low power consumption design, a wide-bit and small driver interface circuit **109** can be provided between the memory chip **100** and the chip **101***a*. The chip **101***a* has multiple input/output (I/O) pads connected to the memory chip **100**, and each of the I/O pads is connected to no ESD protection circuit or a smaller ESD protection circuit and a driver or receiver in the chip **101***a*, and the driver has output capacitance between 0.01 and 10 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF, and the receiver has input capacitance between 0.01 and 20 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF. The memory chip **100** has multiple I/O pads connected to the chip **101***a*, and each of the I/O pads is connected to no ESD protection circuit or a smaller ESD protection circuit, and a driver or receiver in the memory chip **100**, and the driver has output capacitance between 0.01 and 10 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF, and the receiver has input capacitance between 0.01 and 20 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF. The data width between the chip **101***a* and the memory chip **100** can be larger than 2^7, such as 2^7, 2^8, 2^9, 2^{10} or 2^{11}.

[1015] Furthermore, for low power consumption design, there can be provided with a green power supply circuit **108**, such as regulator, with the super discrete capacitor **94** and the super discrete inductor **95** provided on the chip **101***a* using the solder balls **111***e*.

[1016] The chip package **57***a*, for example, can be formed by a suitable process or processes, e.g., by bonding the metal balls, bumps or posts **132** originally formed on a plurality of the memory chip **100** onto multiple contact points, exposed by the openings **980** in the polymer layer **98**, of the patterned circuit layer **801** in the over-passivation scheme **102** of the wafer **10** finalized to be cut into a plurality of the chip **101***a*, for example, shown in FIG. **25**S or **26**J, next flowing the underfill **107** into gaps between the wafer **10** and the plurality of the memory chip **100**, enclosing the metal balls, bumps or posts **132**, next bonding a plurality of the discrete capacitor **94** and a plurality of the discrete inductor **95** onto the contact points, exposed by the openings **980** in the polymer layer **98**, of the patterned circuit layer **801** in the over-passivation scheme **102** of the wafer **10**, for example, shown in FIG. **25**S or **26**J through the solder balls **111***e* using a surface-mount technology (SMT), next cutting the wafer **10** to singularize a plurality of stacked unit including the chips **100** and **101***a*, the discrete capacitor **94** and the discrete inductor **95**, next mounting the stacked unit onto the top side of the BGA substrate **117** by bonding the metal bumps or pillars **27** of the bottom scheme **103** of the chip **101***a* onto the top side of the BGA substrate **117**, next flowing the underfill **107***a* into a gap between the chip **101***a* and the BGA substrate **117**, enclosing the metal bumps or pillars **27**, next forming the molding compound **120** on the top side of the BGA substrate **117**, on the chips **100** and **101***a*, on the discrete capacitor **94** and on the discrete inductor **95**, encapsulating the chips **100** and **101***a*, the discrete capacitor **94** and the discrete inductor **95**, and then forming the solder balls ill b on the bottom side of the BGA substrate **117** by a ball planting process.

[1017] Referring to FIG. **36**C, a chip-package module **118***b* contains a ball-grid-array (BGA) substrate **110**, a stacked unit **136** on the top side of the BGA substrate **110**, a chip package **84***a* on the top side of the BGA substrate **110**, a discrete capacitor **112** over the top side of the BGA substrate **110**, and multiple solder balls **111***a* on the bottom side of the BGA substrate **110**. The discrete capacitor **112** can be provided on and connected to the BGA substrate **110** through multiple solder balls **111***d*. The BGA substrate **110** of the chip-package module **118***b* can be provided on and connected to a substrate, such as printed circuit board, metal substrate, glass substrate or ceramic substrate, through the solder balls **111***a*.

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The solder balls **111***a* and **111***d* may include bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy.

[1018] The chip package **84***a* contains a ball-grid-array (BGA) substrate **113**, two dynamic-random-access-memory (DRAM) chips **140** over the top side of the BGA substrate **113**, two flash memory chips **150** over the DRAM chips **140** and over the BGA substrate **113**, an application-specific-integrated-circuit (ASIC) chip **115** on the top one of the flash memory chips **150**, over the DRAM chips **140** and over the BGA substrate **113**, multiple solder balls **111***c* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on the bottom side of the BGA substrate **113**, and a molding compound **116**, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **113**, encapsulating the chips **140**, **150** and **115**. The BGA substrate **113** of the chip package **84***a* can be provided on and connected to the BGA substrate **110** through the solder balls **111***c*.

[1019] The line **5** shown in FIG. **36**C indicates the previously described passivation layer, and the line **1***a* shown in FIG. **36**C indicates the previously described backside of the thinned silicon substrate **1**. The DRAM chips **140** and the flash memory chips **150** each contain a combination of the previously described thinned silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5**, the previously described over-passivation scheme **102**, multiple through-silicon vias **11** and the previously described bottom scheme **103** including the metal bumps or pillars **27**, and the combination can be referred to one of FIGS. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, and, as shown in these figures, the IC structure **6***a* between the thinned silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuit **43**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. In FIG. **36**C, regarding the chips **140** and **150**, the over-passivation scheme **102** is formed on the passivation layer **5** at the active side of the thinned silicon substrate **1**, and the bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**. Regarding the chips **140** and **150**, the through-silicon vias **11** providing for the previously described vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and/or **11***f* in FIG. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y or **34**G are formed in the thinned silicon substrate **1**, and the specification of the through-silicon vias **11** illustrated in FIG. **36**C can be referred to as the specification of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N, and the process of forming the through-silicon vias **11** as shown in FIG. **36**C can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **1 1***d* and **11***e* as illustrated in FIGS. **24**B-**24**N. Regarding the chips **140** and **150**, the pitch between neighboring two of the metal bumps or pillars **27** can be larger than 10 micrometers, such as between 10 and 100 micrometers. Regarding the chips **140** and **150**, the metal layer of the bottom scheme **103** can be connected to the fine-line scheme **6** of the IC structure **6***a* through the bulk metal layer **9** in the through-silicon vias **11**, and the patterned circuit layer of the over-passivation scheme **102** can be connected to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1020] The chip package **84***a*, for example, can be formed by a suitable process or processes, e.g., by the following steps. First, the metal bumps or pillars **27** originally formed on the DRAM chip **140** (the top one) can be bonded onto multiple contact points of the over-passivation scheme **102** or a wafer, finalized to be cut into a plurality of the DRAM chip **140** (the bottom one), which, for example, can be a plurality of the contact point **801***a* of the patterned circuit layer **801** exposed by the openings **980** in the polymer layer **98**, as shown in FIG. **25**S or **26**J. Next, the metal bumps or pillars **27** originally formed on the flash memory chip **150** (the bottom one) can be bonded onto multiple contact points of the over-passivation scheme **102** of the DRAM chip **140** (the top one), which, for example, can be a plurality of the contact point **801***a* of the patterned circuit layer **801** exposed by the openings **980** in the polymer layer **98**, as shown in FIG. **25**S or **26**J. Next, the metal bumps or pillars **27** originally formed on the flash memory chip **150** (the top one) can be bonded onto multiple contact points of the over-passivation scheme **102** of the flash memory chip **150** (the bottom one), which, for example, can be a plurality of the contact point **801***a* of the patterned circuit layer **801** exposed by the openings **980** in the polymer layer **98**, in, as shown in FIG. **25**S or **26**J. Next, the ASIC chip **115** can be bonded onto multiple contact points of the over-passivation scheme **102** of the flash memory chip **150** (the top one), which, for example, can be a plurality of the contact point **801***a* of the patterned circuit layer **801** exposed by the openings **980** in the polymer layer **98**, as shown in FIG. **25**S or **26**J, through multiple solder balls **111***f* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy, or a tin-silver-copper alloy, on the contact points of the over-passivation scheme **102** of the flash memory chip **150** (the top one), next mounting multiple metal bumps, such as a tin-containing bump, such as a tin-lead alloy, tin-silver alloy or a tin-silver-copper alloy, having a thickness between 10 and 300 micrometers or copper posts having a thickness between 10 and 100 micrometers, preformed on the ASIC chip **115** onto the solder paste, and then reflowing or heating the solder paste to form solid solder balls **111***f* bonding the ASIC chip **115** to the contact points of the top flash memory chip **150**. Next, the wafer can be cut to singularize a plurality of a stacked unit including the two DRAM chips **140**, the two flash memory chips **150** and the ASIC chip **115**. Next, the metal bumps or pillars **27** originally formed on the DRAM chip **140** (the bottom one) in one of the singularized stacked units can be provided on the BGA substrate **113**. Next, the molding compound **116** can be formed on the top side of the BGA substrate **113**, encapsulating the two DRAM chips **140**, the two flash memory chips **150** and the ASIC chip **115** and flowing into a gap between the bottom DRAM chip **140** and the BGA substrate **113**, into a gap between the top DRAM chip **140** and the bottom DRAM chip **140**, into a gap the bottom flash memory chip **150** and the top DRAM chip **140**, into a gap between the top flash memory chip **150** and the bottom flash memory chip **150**, and into a gap between the ASIC chip **115** and the top flash memory chip **150**, enclosing the metal bumps or pillars **27** and the solder balls **111***f*. Next, the solder balls **111***c* can be formed on the bottom side of the BGA substrate **113**.

[1021] The stacked unit **136** contains a memory chip **100***a*, such as dynamic-random-access-memory (DRAM) chip or statistic-random-access-memory (SRAM) chip, a chip **101***b*

on the memory chip **100***a*, a super discrete capacitor **94** on the memory chip **100***a*, and a super discrete inductor **95** on the memory chip **100***a*.

[1022] The chip **101***b* can be a central-processing-unit (CPU) chip designed by x86 architecture, a central-processing-unit (CPU) chip designed by non x86 architectures, such as ARM, Strong ARM or MIPs, a baseband chip, a graphics-processing-unit (GPU) chip, a digital-signal-processing (DSP) chip, a global-positioning-system (GPS) chip, a bluetooth chip, a wireless local area network (WLAN) chip, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any baseband circuit block, a system-on chip (SOC) including a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any graphics-processing-unit (GPU) circuit block, a system-on chip (SOC) including a baseband circuit block, a graphics-processing-unit (GPU) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any wireless local area network (WLAN) circuit block, a system-on chip (SOC) including a baseband circuit block and a wireless local area network (WLAN) circuit block, but not including any graphics-processing-unit (GPU) circuit block and any central-processing-unit (CPU) circuit block, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block and a wireless local area network (WLAN) circuit block, but not including any baseband circuit block and any central-processing-unit (CPU) circuit block, or a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures. Alternatively, the chip **101***b* can be a chip including a central-processing-unit (CPU) circuit block, a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a bluetooth circuit block, a global-positioning-system (GPS) circuit block, and/or a wireless local area network (WLAN) circuit block. The chip **101***b*, graphics-processing-unit (GPU) chip, or the graphics-processing-unit (GPU) circuit block in the chip **101***b* can be designed for 2D or 3D video display, and can be connected to a 3D video display, such as 3D television (3D TV), or a 3D video game player through the BGA substrate **110** and the solder balls **111***a*.

[1023] The memory chip **100***a* contains a combination of the previously described thinned silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5**, the previously described over-passivation scheme **102**, multiple through-silicon vias **11** and the previously described bottom scheme **103** including the metal bumps or pillars **27**, and the combination can be referred to one of FIGS. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, and, as shown in these figures, the IC structure **6***a* between the thinned silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuit **43**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. In FIG. **36**C, regarding the memory chip **100***a*, the over-passivation scheme **102** is formed on the passivation layer **5** at the active side of the thinned silicon substrate **1**, and the bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**. Regarding the memory chip **100***a*, the through-silicon vias **11** providing for the previously described vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and/or **11***f* in FIG. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y or **34**G are formed in the thinned silicon substrate **1**, and the specification of the through-silicon vias **11** illustrated in FIG. **36**C can be referred to as the specification of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N, and the process of forming the through-silicon vias **11** as shown in FIG. **36**C can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N. Regarding the memory chip **100***a*, the pitch between neighboring two of the metal bumps or pillars **27** can be larger than 10 micrometers, such as between 10 and 100 micrometers. Regarding the memory chip **100***a*, the metal layer of the bottom scheme **103** can be connected to the fine-line scheme **6** of the IC structure **6***a* through the bulk metal layer **9** in the through-silicon vias **11** and to the BGA substrate **110** through the metal bumps or pillars **27**, and the metal layer of the over-passivation scheme **102** can be connected to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1024] The stacked unit **136** can be provided on the BGA substrate **110** through the metal bumps or pillars **27** of the bottom scheme **103** of the memory chip **100***a*, and the memory chip **100***a* of the stacked unit **136** can be provided on and connected to the BGA substrate **110** through the metal bumps or pillars **27**. For example, the process for mounting the memory chip **100***a* of the stacked unit **136** onto the top side of the BGA substrate **110** may be performed by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points of the BGA substrate **110**, next mounting the metal bumps or pillars **27** preformed on the memory chip **100***a* onto the solder paste, and then reflowing or heating the solder paste to form a solid solder bonding the metal bumps or pillars **27** to the contact points of the BGA substrate **110**. An underfill **107***b*, such as a polymer, is filled into the gap between the memory chip **100***a* and the top side of the BGA substrate **110**, and encloses the metal bumps or pillars **27**.

[1025] The super discrete capacitor **94** and the super discrete inductor **95** can be provided on and connected to the previously described patterned circuit layer in the over-passivation scheme **102** of the memory chip **100***a* through multiple solder balls **111***e* including bismuth, indium, a tin-silver alloy, a tin-silver-copper alloy or a tin-lead alloy. For example, the process for mounting the discrete capacitor **94** and the discrete inductor **95** on the over-passivation scheme **102** of the memory chip **100***a* can be performed by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points, exposed by the openings **980** in the polymer layer **98**, of the patterned circuit layer **801** in the over-passivation scheme **102**, for example, shown in FIG. **25**S or **26**J, of the memory chip **100***a*, then mounting the discrete capacitor **94** and the discrete inductor **95** onto the solder paste, and then reflowing

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or heating the solder paste to form the solid solder balls **111***e* bonding the discrete capacitor **94** and the discrete inductor **95** to the memory chip **100***a*.

[1026] The chip **101***b* contains a combination of the previously described silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5** and the previously described over-passivation scheme **102**, and the combination can be referred to one of FIGS. **1**B-**1**D, **3**B-**3**D, **5**B, **5**K, **5**S, **5**U-**5**Z, **7**B-**7**D, **8**A-**8**F, **10**A-**10**I, **12**B-**12**D, **14**B-**14**D, **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H, **20** and **23**K, and, as shown in these figures, the IC structure **6***a* between the silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuits **43** and **44**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. Regarding the chip **101***b*, the patterned circuit layer of the over-passivation scheme **102** can be connect to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**, and to the patterned circuit layer of the over-passivation scheme **102** of the memory chip **100***a* through the metal bumps **89** performed on the memory chip **100***a* or the chip **101***b*.

[1027] The chip **101***b* can be provided on and connected to the memory chip **100***a* through the metal bumps **89** performed on the chip **101***b* or the memory chip **100***a*. For example, the process for mounting the chip **101***b* on the memory chip **100***a* can be performed by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points, exposed by the openings **980** in the polymer layer **98**, of the patterned circuit layer **801** in the over-passivation scheme **102**, for example, shown in FIG. **25**S or **26**J, of the memory chip **100***a*, then mounting the metal bumps **89**, for example, shown in FIG. **10**A, **10**B, **10**C, **10**D, **10**E or **15**M, performed on the chip **101***b* onto the solder paste, and then reflowing or heating the solder paste to form a solid solder balls bonding the chip **101***b* to the memory chip **100***a*. Alternatively, the process for mounting the chip **101***b* on the memory chip **100***a* can be performed by screen printing a solder paste, containing a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points, optionally exposed by openings in the topmost polymer layer, of the patterned circuit layer **801**, **802** or **803** or the metal trace **81**, **81**P, **82**, **83**, **83'**, **83***r* or **85** in the over-passivation scheme **102** of the chip **101***b*, then mounting the metal bumps **89**, for example, shown in FIG. **25**T, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y or **34**G, performed on the memory chip **100***a* onto the solder paste, and then reflowing or heating the solder paste to form a solid solder balls bonding the chip **101***b* to the memory chip **100***a*. An underfill **106**, such as a polymer, can be filled into the gap between the memory chip **100***a* and the chip **101***b*, encapsulating the metal bumps **89** performed on the memory chip **100***a* or the chip **101***b*.

[1028] Furthermore, for low power consumption design, a wide-bit and small driver interface circuit **109** can be provided between the memory chip **100***a* and the chip **101***b*. The chip **101***b* has multiple I/O pads connected to the memory chip **100***a*, and each of the I/O pads is connected to no ESD protection circuit or a smaller ESD protection circuit and a driver or receiver in the chip **101***b*, and the driver has output capacitance between 0.01 and 10 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF, and the receiver has input capacitance between 0.01 and 20 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF. The memory chip **100***a* has multiple I/O pads connected to the chip **101***b*, and each of the I/O pads is connected to no ESD protection circuit or a smaller ESD protection circuit, and a driver or receiver in the memory chip **100***a*, and the driver has output capacitance between 0.01 and 10 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF, and the receiver has input capacitance between 0.01 and 20 pF, preferably between 0.1 and 10 pF, preferably between 0.1 and 5 pF, preferably between 0.1 and 3 pF, preferably between 0.1 and 2 pF, preferably between 0.1 and 1 pF, and preferably between 0.01 and 1 pF. The data width between the chip **101***b* and the memory chip **100***a* can be larger than 2^7, such as 2^7, 2^8, 2, 2^{10} or 2^{11}.

[1029] Furthermore, for low power consumption design, there can be provided with a green power supply circuit, such as regulator, with the super discrete capacitor **94** and the super discrete inductor **95** provided on the memory chip **100***a* using the solder balls **111***e*.

[1030] The stacked unit **136**, for example, can be formed by a suitable process or processes, e.g., by bonding the metal bumps **89** originally formed on a plurality of the chip **101***b* onto multiple contact points, optionally exposed by the openings **980** in the polymer layer **98**, of the patterned circuit layer **801** in the over-passivation scheme **102** of the wafer **10** finalized to be cut into a plurality of the memory chip **100***a*, for example, shown in FIG. **25**S or **26**J, next flowing the underfill **106** into gaps between the wafer **10** and the plurality of the chip **101***b*, enclosing the metal bumps **89**, next bonding a plurality of the discrete capacitor **94** and a plurality of the discrete inductor **95** onto the contact points, exposed by the openings **980** in the polymer layer **98**, of the patterned circuit layer **801** in the over-passivation scheme **102** of the wafer **10**, for example, shown in FIG. **25**S or **26**J, through the solder balls **111***e* using a surface-mount technology (SMT), and then cutting the wafer **10** to singularize a plurality of the stacked unit **136** including the chips **100***a* and **101***b*, the discrete capacitor **94** and the discrete inductor **95**.

[1031] Referring to FIG. **36**D, a chip-package module **118***c* contains a ball-grid-array (BGA) substrate **110**, the chip package **57***a* illustrated in FIG. **36**B on the top side of the BGA substrate **110**, the chip package **84***a* illustrated in FIG. **36**C on the top side of the BGA substrate **110**, a discrete capacitor **112** over the top side of the BGA substrate **110**, and multiple solder balls **111***a* on the bottom side of the BGA substrate **110**. The discrete capacitor **112** can be provided on and connected to the BGA substrate **110** through multiple solder balls **111***d*. The BGA substrate **110** of the chip-package module **118***c* can be provided on and connected to a substrate, such as printed circuit board, metal substrate, glass substrate or ceramic substrate, through the solder balls **111***a*. The specification of the chip package **57***a* illustrated in FIG. **36**D can be referred to as the specification of the chip package **57***a* as illustrated in FIG. **36**B, and the process of forming the chip package **57***a* as shown in FIG. **36**D can be referred to as

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the process of forming the chip package **57***a* as illustrated in FIG. **36**B. The specification of the chip package **84***a* illustrated in FIG. **36**D can be referred to as the specification of the chip package **84***a* as illustrated in FIG. **36**C, and the process of forming the chip package **84***a* as shown in FIG. **36**D can be referred to as the process of forming the chip package **84***a* as illustrated in FIG. **36**C. The BGA substrate **117** of the chip package **57***a* can be provided on and connected to the BGA substrate **110** through the solder balls **111***b*. The BGA substrate **113** of the chip package **84***a* can be provided on and connected to the BGA substrate **110** through the solder balls **111***c*. The solder balls **111***a*, **111***b*, **111***c* and **111***d* may include bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The line **5** shown in FIG. **36**D indicates the previously described passivation layer at the thinned silicon substrate **1**, and the line **1***a* shown in FIG. **36**D indicates the previously described backside of the thinned silicon substrate **1**.

[1032] Referring to FIG. **37**A, a module **137** contains a substrate **301**, a wirebonded stacked memory ball-grid-array (BGA) package **138** provided on the top side of the substrate **301**, a stacked dynamic-random-access-memory (DRAM) ball-grid-array (BGA) package **139** provided on the top side of the substrate **301**, a processor unit **303** provided on the top side of the substrate **301**, a discrete device **305** provided on the back side of the substrate **301** through solder balls **111***g* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, two connectors **307** and **309** connected to the substrate **301**, a radio frequency (RF) module **325** provided on the back side of the substrate **301** through solder balls **111***m* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, multiple peripheral or communication devices (not shown), such as Bluetooth chips or wireless communication devices, provided on the top side and/or back side of the substrate **301** through solder balls containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, and multiple power supply devices (not shown), such as power management chips, provided on the top side and/or back side of the substrate **301** through solder balls containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy.

[1033] The substrate **301** may contain an epoxy-based polymer, such as BT epoxy. The discrete device **305** can be a discrete capacitor or a discrete inductor, and can be connected to the substrate **301** through the solder balls **111***g*. Alternatively, the discrete device **305** can be provided on the top side of the substrate **301** through the solder balls **111***g*. The wirebonded stacked memory BGA package **138** is used as a mass storage, and the stacked DRAM BGA package **139** is used as a main memory.

[1034] The RF module **325** can be connected to the substrate **301** through the solder balls **111***m*. The RF module **325**, in side by side multi-chip modules (MCM) format, may include a ball-grid-array (BGA) substrate **327** provided on the back side of the substrate **301** through the solder balls **111***m*, a radio frequency (RF) chip **328***a* provided on the BGA substrate **327** by using a glue material, a radio frequency (RF) chip **328***b* provided on the BGA substrate **327** through multiple solder balls **111***n* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, and two discrete components **329***a* and **329***b* provided on the BGA substrate **327** through solder balls **1110** containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The RF chip **328***a* can be connected to the BGA substrate **327** by bonding multiple wirebonding wires **119***c*, such as gold wires or copper wires, to the RF chip **328***a* and to the BGA substrate **327**. The RF chip **328***b* can be connected to the BGA substrate **327** through the solder balls **111***n*. The discrete component **329***a*, such as discrete capacitor, discrete inductor or discrete resistor, can be connected to the BGA substrate **327** through the solder balls **111***o*. The discrete component **329***b*, such as discrete capacitor, discrete inductor or discrete resistor, can be connected to the BGA substrate **327** through the solder balls **111***o*. Both of the RF chips **328***a* and **328***b* may include a radio frequency (RF) power amplifier, a radio frequency (RF) transceiver, a radio frequency (RF) driver amplifier, a balun circuit, a surface acoustic wave (SAW) filter, a filter, a coupler, and/or an isolator.

[1035] The RF module **325** is used for transmitting or receiving RF (voice and/or data) signals for Wireless LAN (WLAN) communication and/or mobile phone communication, such as 3G CDMA (Code Division Multiple Access) or TDMA GSM (Time Division Multiple Access Global System for Mobile communication).

[1036] The connector **307** can be connected to external circuits of elements on a substrate, such as printed circuit board (PCB), for power supply or for external signals. The connector **307** can be universal serial bus (USB), such as USB 2.0 or USB 3.0, high-definition multimedia interface (HDMI), DisplayPort or IEEE 1394. Alternatively, the connector **307** can be an optical connector, such as Light Peak. The connector **307** can be connected to a charger, a 3D video game player, or a 3D video display, such as 3D television (3D TV). The connector **309** can be connected to a display, such as flat panel display, liquid crystal display (LCD) or 3D display.

[1037] The wirebonded stacked memory BGA package **138** contains a ball-grid-array (BGA) substrate **113***a*, multiple memory chips **104***a*, **104***b*, **104***c* and **104***d* over the top side of the BGA substrate **113***a*, multiple solder balls **111***h* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on the bottom side of the BGA substrate **113***a*, multiple wirebonded wires **119***b*, such as gold wires, copper wires or aluminum wires, connecting one of the memory chips **104***a*, **104***b*, **104***c* and **104***d* to the other one of the memory chips **104***a*, **104***b*, **104***c* and **104***d* or to the BGA substrate **113***a*, and a molding compound **116**, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **113***a*, on the wirebonded wires **119***b* and on the memory chips **104***a*, **104***b*, **104***c* and **104***d*, encapsulating the wirebonded wires **119***b* and the memory chips **104***a*, **104***b*, **104***c* and **104***d*. The wirebonded stacked memory BGA package **138** can be provided on and connected to the substrate **301** through the solder balls **111***h* formed on the bottom side of the BGA substrate **113***a*. The BGA substrate **113***a* may contain an epoxy-based polymer, such as BT epoxy. Each of the memory chips **104***a*, **104***b*, **104***c* and **104***d* can be a flash memory chip or a dynamic-random-access-memory (DRAM) chip. Each of the memory chips **104***a*, **104***b*, **104***c* and **104***d* may have a memory size larger than 512K bits, such as between 512K bits and 256 G bits.

[1038] The memory chips **104***a*, **104***b*, **104***c* and **104***d* each contain a combination of the previously described silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5** and the previously described over-passivation scheme **102**, and the combination can be referred to one of FIGS. **1**B-**1**D, **3**B-**3**D, **5**B, **5**K, **5**S, **5**U-**5**Z, **7**B-**7**D, **8**A-**8**F, **10**A-**10**I, **12**B-**12**D, **14**B-**14**D, **15**H, **15**K-**15**M, **16**L, **16**M,

17J, **18**I, **19**H, **20** and **23**K, and, as shown in these figures, the IC structure **6***a* that is over the silicon substrate **1** and under the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuits **43** and **44**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. Regarding the memory chips **104***a*, **104***b*, **104***c* and **104***d*, the patterned circuit layer of the over-passivation scheme **102** can be connect to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**. The line **5** shown in FIG. **37**A indicates the previously described passivation layer.

[1039] The memory chip **104***a* can be mounted onto the BGA substrate **113***a* by adhering the silicon substrate **1** of the memory chip **104***a* to the top side of the BGA substrate **113***a* using a film **135** of a glue material, such as a polymer or an epoxy-based material, with a thickness between 1 and 50 micrometers. The memory chip **104***b* can be mounted onto the memory chip **104***a* by adhering the silicon substrate **1** of the memory chip **104***b* to the over-passivation scheme **102** of the memory chip **104***a* using another film **135** of the glue material. The memory chip **104***c* can be mounted onto the memory chip **104***b* by adhering the silicon substrate **1** of the memory chip **104***c* to the over-passivation scheme **102** of the memory chip **104***b* using another film **135** of the glue material. The memory chip **104***d* can be mounted onto the memory chip **104***c* by adhering the silicon substrate **1** of the memory chip **104***d* to the over-passivation scheme **102** of the memory chip **104***c* using another film **135** of the glue material.

[1040] The memory chip **104***b* has a right portion overhanging the memory chip **104***a*, and the memory chip **104***a* has a left portion not vertically under the memory chip **104***b*. The memory chip **104***b* has a left sidewall recessed from that of the memory chip **104***a*. The memory chip **104***c* has a right portion overhanging the memory chip **104***b*, and the memory chip **104***b* has a left portion not vertically under the memory chip **104***c*. The memory chip **104***c* has a left sidewall recessed from that of the memory chip **104***b*. The memory chip **104***d* has a right portion overhanging the memory chip **104***c*, and the memory chip **104***c* has a left portion not vertically under the memory chip **104***d*. The memory chip **104***d* has a left sidewall recessed from that of the memory chip **104***c*.

[1041] The memory chips **104***a*, **104***b*, **104***c* and **104***d* can be connected to the BGA substrate **113***a* through the wirebonded wires **119***b*, and to the substrate **301** through the wirebonded wires **119***b*, the BGA substrate **113***a* and the solder balls **111***h*.

[1042] The wirebonded stacked memory BGA package **138** contains four memory chips **104***a*, **104***b*, **104***c* and **104***d*. Alternatively, the wirebonded stacked memory BGA package **138** may contain more than four memory chips. For example, other four memory chips can be stacked over the four memory chips **104***a*, **104***b*, **104***c* and **104***d*, and the other four memory chips can be connected to each other, to the four memory chips **104***a*, **104***b*, **104***c* and **104***d* and/or to the BGA substrate **113***a* through wirebonded wires, like the wirebonded wires **119***b*. Accordingly, eight stacked memory chips can be provided on the BGA substrate **113***a*. Alternatively, other eight memory chips can be stacked over the eight stacked memory chips, and the other eight memory chips can be connected to each other, to the eight memory chips or to the BGA substrate **113***a* through wirebonded wires, like the wirebonded wires **119***b*. Accordingly, sixteen stacked memory chips can be provided on the BGA substrate **113***a*. As mentioned above, multiple stacked memory chips, such as ranging **4** to **16** stacked memory chips, can be provided over the BGA substrate **113***a*.

[1043] One of the wirebonded wires **119***b*, for example, can be bonded on the bulk metal layer **8012** of the patterned circuit layer **801** in the over-passivation scheme **102**, on the bulk metal layer **8022** of the patterned circuit layer **802** in the over-passivation scheme **102**, on the bulk metal layer **8032** of the patterned circuit layer **803** in the over-passivation scheme **102**, on the metal trace **81** in the over-passivation scheme **102**, on the metal trace **81**P in the over-passivation scheme **102**, on the metal trace **82** in the over-passivation scheme **102**, on the metal trace **83** in the over-passivation scheme **102**, on the metal trace **83'** in the over-passivation scheme **102**, on the metal trace **83***r* in the over-passivation scheme **102**, or on the metal trace **85** in the over-passivation scheme **102**, to connect one of the memory chips **104***a*, **104***b*, **104***c* and **104***d* to the other one of the memory chips **104***a*, **104***b*, **104***c* and **104***d* or to the BGA substrate **113***a*.

[1044] The stacked DRAM BGA package **139** contains a ball-grid-array (BGA) substrate **113***b*, multiple dynamic-random-access-memory (DRAM) chips **140**, **140***a*, **140***b* and **140***c* over the top side of the BGA substrate **113***b*, multiple solder balls **111***k* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on the bottom side of the BGA substrate **113***b*, and a molding compound **116***a*, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **113***b* and on the DRAM chip **140***c*, encapsulating the DRAM chips **140**, **140***a*, **140***b* and **140***c*. The stacked DRAM BGA package **139** can be provided on and connected to the substrate **301** through the solder balls **111***k*. The BGA substrate **113***b* may contain an epoxy-based polymer, such as BT epoxy. Each of the DRAM chips **140**, **140***a*, **140***b* and **140***c* may have a memory size larger than 512K bits, such as between 512K bits and 256 G bits.

[1045] The DRAM chip **140** contains a combination of the previously described thinned silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5**, the previously described over-passivation scheme **102**, multiple through-silicon vias **11** and the previously described bottom scheme **103** including the metal bumps or pillars **27**, and the combination can be referred to one of FIGS. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, and, as shown in these figures, the IC structure **6***a* between the thinned silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuit **43**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. In FIG. **37**A, regarding the DRAM chip **140**, the over-passivation scheme **102** is formed on the passivation layer **5** at the active side of the thinned silicon substrate **1**, and the bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**. Regarding the DRAM chip **140**, the through-silicon vias **11** providing for the previously described vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and/or **11***f* in FIG. **25**S, **25**T, **26**J, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y or **34**G are formed in the thinned silicon substrate **1**, and the specification

of the through-silicon vias **11** illustrated in FIG. **37**A can be referred to as the specification of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N, and the process of forming the through-silicon vias **11** as shown in FIG. **37**A can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N. Regarding the DRAM chip **140**, the metal layer of the bottom scheme **103** can be connected to the fine-line scheme **6** of the IC structure **6***a* through the bulk metal layer **9** in the through-silicon vias **11**, and the patterned circuit layer of the over-passivation scheme **102** can be connected to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1046] The DRAM chip **140** can be provided on and connected to the BGA substrate **113***b* through the metal bumps or pillars **27** of the DRAM chip **140**, and a layer **401** of a dielectric, such as a polymer, polyimide, benzocyclobutene, polybenzoxazole, an underfill or silicon oxide, can be optionally formed in a gap between the DRAM chip **140** and the BGA substrate **113***b*, encapsulating the metal bumps or pillars **27**. For example, the process for mounting the DRAM chip **140** onto the BGA substrate **113***b* may be performed by screen printing a solder paste, containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points of the BGA substrate **113***b*, then mounting the metal bumps or pillars **27** preformed on the DRAM chip **140** onto the solder paste, and then reflowing or heating the solder paste to form solid solder balls, containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, bonding the metal bumps or pillars **27** to the contact points of the BGA substrate **113***b*.

[1047] The DRAM chip **140***a* contains a combination of the previously described thinned silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5**, the previously described over-passivation scheme **102** including the metal bumps **89**, multiple through-silicon vias **11** and the previously described bottom scheme **103** including the metal bumps or pillars **27**, and the combination can be referred to one of FIGS. **25**T, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, and, as shown in these figures, the IC structure **6***a* between the thinned silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuit **43**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. In FIG. **37**A, regarding the DRAM chip **140***a*, the over-passivation scheme **102** is formed on the passivation layer **5** at the active side of the thinned silicon substrate **1**, and the bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**. Regarding the DRAM chip **140***a*, the through-silicon vias **11** providing for the previously described vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and/or **11***f* in FIG. **25**T, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y or **34**G are formed in the thinned silicon substrate **1**, and the specification of the through-silicon vias **11** illustrated in FIG. **37**A can be referred to as the specification of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N, and the process of forming the through-silicon vias **11** as shown in FIG. **37**A can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N. Regarding the DRAM chip **140***a*, the metal layer of the bottom scheme **103** can be connected to the fine-line scheme **6** of the IC structure **6***a* through the bulk metal layer **9** in the through-silicon vias **11**, and the patterned circuit layer of the over-passivation scheme **102** can be connected to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1048] The DRAM chip **140***a* can be provided on and connected to the DRAM chip **140** through the metal bumps or pillars **27** of the DRAM chip **140***a*, and another layer **401** of the dielectric can be optionally formed in a gap between the DRAM chips **140** and **140***a*, encapsulating the metal bumps or pillars **27**. For example, the process for mounting the DRAM chip **140***a* onto the DRAM chip **140** may be performed by screen printing a solder paste, containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points, optionally exposed by openings in the topmost polymer layer, of the patterned circuit layer **801** in the over-passivation scheme **102** of the DRAM chip **140**, then mounting the metal bumps or pillars **27** preformed on the DRAM chip **140***a* onto the solder paste, and then reflowing or heating the solder paste to form solid solder balls, containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, bonding the metal bumps or pillars **27** to the contact points of the patterned circuit layer in the over-passivation scheme **102** of the DRAM chip **140**. Alternatively, the process for mounting the DRAM chip **140***a* onto the DRAM chip **140** may be performed by bonding the metal bumps or pillars **27** performed on the DRAM chip **140***a* with the metal bumps **89**, for example, shown in FIGS. **25**T, **26**K, **27**T, **28**I, **30**L, **31**I, **32**T, **33**W, **33**Y and **34**G, performed on the DRAM chip **140**.

[1049] The DRAM chip **140***b* contains a combination of the previously described thinned silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5**, the previously described metal pads, bumps or traces **34***a*, multiple through-silicon vias **11** and the previously described bottom scheme **103** including the metal bumps or pillars **27**, and the combination can be referred to one of FIGS. **25**N, **25**R, **26**I, **27**S, **28**H, **30**N, **31**J, **32**U and **33**U, and, as shown in these figures, the IC structure **6***a* between the thinned silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuit **43**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. Regarding the DRAM chip **140***b*, the metal pads, bumps or traces **34***a* are formed at the active side of the thinned silicon substrate **1**, and the bottom scheme **103** is formed at the backside **1***a* of the thinned silicon substrate **1**. Regarding the DRAM chip **140***b*, the through-silicon vias **11** providing for the previously described vias **11***a*, **11***b*, **11***c*, **11***d*, **11***e* and/or **11***f* in FIG. **25**N, **25**R, **26**I, **27**S, **28**H, **30**N, **31**J, **32**U or **33**U are formed in the thinned silicon substrate **1**, and the specification of the through-silicon vias **11** illustrated in FIG. **37**A can be referred to as the specification of the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N, and the process of forming the through-silicon vias **11** as shown in FIG. **37**A can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* as illustrated in FIGS. **24**B-**24**N. Regarding the DRAM chip **140***b*, the metal layer of the bottom scheme **103** can be connected to the

fine-line scheme **6** of the IC structure **6***a* through the bulk metal layer **9** in the through-silicon vias **11**, and the metal pads, bumps or traces **34***a* can be connected to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1050] The DRAM chip **140***b* can be mounted onto and connected to the DRAM chip **140***a* through the metal bumps or pillars **27** of the DRAM chip **140***a* and through the metal pads, bumps or traces **34***a* of the DRAM chip **140***b* by bonding the metal pads, bumps or traces **34***a* onto the metal bumps or pillars **27**. Another layer **401** of the dielectric can be optionally formed in a gap between the DRAM chips **140***a* and **140***b*, encapsulating the metal bumps or pillars **27** and the metal pads, bumps or traces **34***a*.

[1051] The DRAM chip **140***c* contains a combination of the previously described silicon substrate **1**, an IC structure **6***a*, the previously described passivation layer **5** and the previously described over-passivation scheme **102**, and the combination can be referred to one of FIGS. **1**B-**1**D, **3**B-**3**D, **5**B, **5**K, **5**S, **5**U-**5**Z, **7**B-**7**D, **8**A-**8**F, **10**A-**10**I, **12**B-**12**D, **14**B-**14**D, **15**H, **15**K-**15**M, **16**L, **16**M, **17**J, **18**I, **19**H, **20** and **23**K, and, as shown in these figures, the IC structure **6***a* between the silicon substrate **1** and the passivation layer **5** may include the previously described internal circuits **21**, **22**, **23** and **24**, the previously described voltage regulator or converter circuit **41**, the previously described off-chip buffer **42**, the previously described ESD circuits **43** and **44**, the previously described dielectric layers **30**, the previously described vias **30'**, the previously described fine-line scheme **6** including the fine-line metal layers **60** and the fine-line via plugs **60'**, and etc. In FIG. **37**A, regarding the DRAM chip **140***c*, the over-passivation scheme **102** is formed under the passivation layer **5** at the active side of the silicon substrate **1**. Regarding the DRAM chip **140***c*, the patterned circuit layer of the over-passivation scheme **102** can be connect to the fine-line scheme **6** of the IC structure **6***a* through openings in the passivation layer **5**.

[1052] The DRAM chip **140***c* can be provided on and connected to the DRAM chip **140***b* through the metal bumps or pillars **27** of the DRAM chip **140***b*, and another layer **401** of the dielectric can be optionally formed in a gap between the DRAM chips **140***b* and **140***c*, encapsulating the metal bumps or pillars **27**. For example, the process for mounting the DRAM chip **140***c* onto the DRAM chip **140***b* may be performed by screen printing a solder paste, containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, on multiple contact points in the over-passivation scheme **102** of the DRAM chip **140***c*, then bonding the metal bumps or pillars **27** preformed on the DRAM chip **140***b* with the solder paste, and then reflowing or heating the solder paste to form solid solder balls, containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy, bonding the metal bumps or pillars **27** to the contact points of the DRAM chip **140***c*. Alternatively, the process for mounting the DRAM chip **140***c* onto the DRAM chip **140***b* may be performed by bonding the metal bumps **89**, which can be referred to FIGS. **8**A-**8**F, **10**A-**10**E, **15**L, **15**M, **16**M and **20**, provided by the over-passivation scheme **102** of the DRAM chip **140***c* onto the metal bumps or pillars **27** of the DRAM chip **140***b*.

[1053] The DRAM chip **140***c* can be connected to the BGA substrate **113***b* through the bulk metal layer **9** in the through-silicon vias **11** provided by the DRAM chips **140***b*, **140***a* and **140** and through the metal bumps or pillars **27** provided by the DRAM chips **140***b*, **140***a* and **140**. The DRAM chip **140***b* can be connected to the BGA substrate **113***b* through the bulk metal layer **9** in the through-silicon vias **11** provided by the DRAM chips **140***a* and **140** and through the metal bumps or pillars **27** provided by the DRAM chips **140***a* and **140**. The DRAM chip **140***a* can be connected to the BGA substrate **113***b* through the bulk metal layer **9** in the through-silicon vias **11** provided by the DRAM chip **140** and through the metal bumps or pillars **27** provided by the DRAM chip **140**.

[1054] The stacked DRAM BGA package **139** contains four DRAM chips **140**, **140***a*, **140***b* and **140***c*. Alternatively, the stacked DRAM BGA package **139** may contain more than four DRAM chips. For example, other four DRAM chips can be stacked over the four DRAM chips **140**, **140***a*, **140***b* and **140***c*, and the other four DRAM chips can be connected to each other, to the four DRAM chips **140**, **140***a*, **140***b* and **140***c* and to the BGA substrate **113***b* through metal interconnects, such as the previously described metal bumps or pillars **27**, the previously described metal bumps **89**, copper bumps having a thickness between 5 and 50 micrometers or between 10 and 100 micrometers, nickel bumps having a thickness between 5 and 50 micrometers or between 10 and 100 micrometers, gold bumps having a thickness between 5 and 30 micrometers or between 10 and 100 micrometers, solder bumps having a thickness between 5 and 50 micrometers or between 10 and 200 micrometers, or the below-mentioned microbumps **317**, between the neighboring two DRAM chips. Accordingly, eight stacked DRAM chips can be provided on the BGA substrate **113***b*. Alternatively, other eight DRAM chips can be stacked over the eight stacked DRAM chips, and the other eight DRAM chips can be connected to each other, to the eight DRAM chips and to the BGA substrate **113***b* through metal interconnects, such as the previously described metal bumps or pillars **27**, the previously described metal bumps **89**, copper bumps having a thickness between 5 and 50 micrometers or between 10 and 100 micrometers, nickel bumps having a thickness between 5 and 50 micrometers or between 10 and 100 micrometers, gold bumps having a thickness between 5 and 30 micrometers or between 10 and 100 micrometers, solder bumps having a thickness between 5 and 50 micrometers or between 10 and 200 micrometers, or the below-mentioned microbumps **317**, between the neighboring two DRAM chips. Accordingly, sixteen stacked DRAM chips can be provided on the BGA substrate **113***b*. As mentioned above, multiple stacked DRAM chips, such as ranging 4 to 16 stacked DRAM chips, can be provided over the BGA substrate **113***b*.

[1055] The BGA substrate **113***b* can be replaced with a silicon substrate with through-silicon vias, and the DRAM chip **140** can be provided on and connected to the silicon substrate through the metal bumps or pillars **27** of the DRAM chip **140**. Alternatively, the BGA substrate **113***b* can be replaced with a glass substrate with through vias, and the DRAM chip **140** can be provided on and connected to the glass substrate through the metal bumps or pillars **27** of the DRAM chip **140**. Alternatively, the BGA substrate **113***b* can be replaced with a metal substrate with an insulating material, and the DRAM chip **140** can be provided on and connected to the metal substrate through the metal bumps or pillars **27** of the DRAM chip **140**. Alternatively, the BGA substrate **113***b* can be replaced with a ceramic substrate, and the DRAM chip **140** can be provided on and connected to the ceramic substrate through the metal bumps or pillars **27** of the DRAM chip **140**. The previously described silicon substrate, glass

substrate, metal substrate or ceramic substrate can be provided on and connected to the substrate **301** through the solder balls **111***k*.

[1056] The processor unit **303** may contain a cache memory chip **311**, a chip **313** on the cache memory chip **311**, a cache memory chip **321** on the chip **313**, and a heat spreader or heat sink **315** on the cache memory chip **321**. The cache memory chip **311** may include a bottom scheme **103** with multiple metal bumps or pillars **27**, and the cache memory chip **311** can be provided on and connected to the substrate **301** through the bumps or pillars **27**. An underfill **107***c*, such as a polymer, can be filled into a gap between the cache memory chip **311** and the substrate **301**, and encloses the metal bumps or pillars **27**.

[1057] The chip **313** can be provided on and connected to the cache memory chip **311** through multiple microbumps **317** with a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers. A pitch between neighboring two microbumps **317** can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. The microbumps **317** can be between metal pads **600***b* of the cache memory chip **311** and metal pads **600***c* of the chip **313**, and the metal pads **600***b* of the cache memory chip **311** can be connected to the metal pads **600***c* of the chip **313** through the microbumps **317**. For example, each of the microbumps **317** may include two nickel layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, and a solder including antimony, bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, between the two nickel layers. Alternatively, each of the microbumps **317** may include two copper layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, and a solder including antimony, bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, between the two copper layers. Alternatively, each of the microbumps **317** may include two copper layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, two nickel layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, between the two copper layers, and a solder including antimony, bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, between the two nickel layers. An underfill **107***d* without fillers, such as a polymer, is filled into a gap between the cache memory chip **311** and the chip **313**, and encloses the microbumps **317**.

[1058] The cache memory chip **321** can be provided on and connected to the chip **313** through multiple microbumps **317***a* with a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers. A pitch between neighboring two microbumps **317***a* can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. Each of the microbumps **317***a* can be between a metal pad **600***d* of the cache memory chip **321** and a contact point of a bottom scheme **103** of the chip **313**, and the metal pad **600***d* of the cache memory chip **321** can be connected to the contact point of the bottom scheme **103** of the chip **313** through the microbump **317***a*. For example, each of the microbumps **317***a* may include two nickel layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, and a solder including antimony, bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, between the two nickel layers. Alternatively, each of the microbumps **317***a* may include two copper layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, and a solder including antimony, bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, between the two copper layers. Alternatively, each of the microbumps **317***a* may include two copper layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, two nickel layers each having a thickness larger than 2 micrometers, such as between 2 and 20 micrometers, between the two copper layers, and a solder including antimony, bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, between the two nickel layers. An underfill **107***e* without fillers, such as a polymer, is filled into a gap between the chip **313** and the cache memory chip **321**, and encloses the microbumps **317***a*.

[1059] The heat spreader or heat sink **315** can be mounted onto the cache memory chip **321** by adhering the heat spreader or heat sink **315** to the cache memory chip **321** using a film **319** of a glue material, such as a polymer or an epoxy-based material, with a thickness between 1 and 50 micrometers.

[1060] Alternatively, referring to FIG. **38**A, the substrate **301** shown in FIG. **37**A can be replaced with a ball-grid-array (BGA) substrate **302**. Multiple solder balls **111***z* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy can be provided on the back side of the BGA substrate **302**. Each of the solder balls **111***z* has a width larger than that of each of the solder balls **111***h* and **111***k*. The module **137** shown in FIG. **38**A is designed with the solder balls **111***z* to connect with external circuits instead of the connectors **307** and **309** shown in FIG. **37**A, that is, the module **137** shown in FIG. **38**A can be connected to a charger, a 3D video game player, a 3D video display, such as 3D television (3D TV), or a display, such as flat panel display, liquid crystal display (LCD) or 3D display, through the solder balls **111***z*. The element in FIG. **38**A indicated by a same reference number as indicates the element in FIG. **37**A has a same material and spec as the element illustrated in FIG. **37**A.

[1061] FIG. **37**B shows another example of the module **137**. The module **137** shown in FIG. **37**B is similar to that shown in FIG. **37**A except that there is no cache memory chip **321** provided on the chip **313**, and the heat spreader or heat sink **315** is mounted onto the chip **313** using the film **319** of the glue material. The element in FIG. **37**B indicated by a same reference number as indicates the element in FIG. **37**A has a same material and spec as the element illustrated in FIG. **37**A.

[1062] Alternatively, referring to FIG. **38**B, the substrate **301** shown in FIG. **37**B can be replaced with a ball-grid-array (BGA) substrate **302**. Multiple solder balls **111***z* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy can be provided on the back side of the BGA substrate **302**. Each of the solder balls **111***z* has a width

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larger than that of each of the solder balls **111***h* and **111***k*. The module **137** shown in FIG. **38**B is designed with the solder balls **111***z* to connect with external circuits instead of the connectors **307** and **309** shown in FIG. **37**B, that is, the module **137** shown in FIG. **38**B can be connected to a charger, a 3D video game player, a 3D video display, such as 3D television (3D TV), or a display, such as flat panel display, liquid crystal display (LCD) or 3D display, through the solder balls **111**Z. The element in FIG. **38**B indicated by a same reference number as indicates the element in FIGS. **37**A and **37**B has a same material and spec as the element illustrated in FIGS. **37**A and **37**B.

[1063] FIG. **37**C shows another example of the module **137**. The module **137** shown in FIG. **37**C is similar to that shown in FIG. **37**B except that the cache memory chip **311** is mounted onto the substrate **301** by adhering the cache memory chip **311** to the top side of the substrate **301** using a glue material **319***a*, the cache memory chip **311** is connected to the substrate **301** by wirebonding two wires **119***c*, such as gold wires or copper wires, to the testing metal pads **600***s* and **600***t* of the cache memory chip **311** and to the substrate **301**, and a molding compound **323** is formed on the substrate **301**, encapsulating the wirebonded wires **119***c* and the chips **311**, **313** and **321**. The heat spreader or heat sink **315** has a surface **315***a* uncovered by the molding compound **323** and substantially coplanar with a top surface **323***a* of the molding compound **323**. The glue material **319***a* can be a polymer or an epoxy-based material with a thickness between 1 and 50 micrometers. The molding compound **323** can be a polymer or an epoxy-based material. The element in FIG. **37**C indicated by a same reference number as indicates the element in FIGS. **37**A and **37**B has a same material and spec as the element illustrated in FIGS. **37**A and **37**B.

[1064] Alternatively, referring to FIG. **38**C, the substrate **301** shown in FIG. **37**C can be replaced with a ball-grid-array (BGA) substrate **302**. Multiple solder balls **111***z* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy can be provided on the back side of the BGA substrate **302**. Each of the solder balls **111***z* has a width larger than that of each of the solder balls **111***h* and **111***k*. The module **137** shown in FIG. **38**C is designed with the solder balls **111***z* to connect with external circuits instead of the connectors **307** and **309** shown in FIG. **37**C, that is, the module **137** shown in FIG. **38**C can be connected to a charger, a 3D video game player, a 3D video display, such as 3D television (3D TV), or a display, such as flat panel display, liquid crystal display (LCD) or 3D display, through the solder balls **111**Z. The element in FIG. **38**C indicated by a same reference number as indicates the element in FIGS. **37**A, **37**B and **37**C has a same material and spec as the element illustrated in FIGS. **37**A, **37**B and **37**C.

[1065] FIG. **37**D shows another example of the module **137**. The module **137** shown in FIG. **37**D is similar to that shown in FIG. **37**A except that the cache memory chip **311** is mounted onto the substrate **301** by adhering the cache memory chip **311** to the top side of the substrate **301** using a glue material **319***a*, the cache memory chip **311** is connected to the substrate **301** by wirebonding two wires **119***c*, such as gold wires or copper wires, to the testing metal pads **600***s* and **600***t* of the cache memory chip **311** and to the substrate **301**, and a molding compound **323** is formed on the substrate **301**, encapsulating the wirebonded wires **119***c* and the chips **311**, **313** and **321**. The heat spreader or heat sink **315** has a surface **315***a* uncovered by the molding compound **323** and substantially coplanar with a top surface **323***a* of the molding compound **323**. The glue material **319***a* can be a polymer or an epoxy-based material with a thickness between 1 and 50 micrometers. The molding compound **323** can be a polymer or an epoxy-based material. The element in FIG. **37**D indicated by a same reference number as indicates the element in FIG. **37**A has a same material and spec as the element illustrated in FIG. **37**A.

[1066] Alternatively, referring to FIG. **38**D, the substrate **301** shown in FIG. **37**D can be replaced with a ball-grid-array (BGA) substrate **302**. Multiple solder balls **111***z* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy can be provided on the back side of the BGA substrate **302**. Each of the solder balls **111***z* has a width larger than that of each of the solder balls **111***h* and **111***k*. The module **137** shown in FIG. **38**D is designed with the solder balls **111***z* to connect with external circuits instead of the connectors **307** and **309** shown in FIG. **37**D, that is, the module **137** shown in FIG. **38**D can be connected to a charger, a 3D video game player, a 3D video display, such as 3D television (3D TV), or a display, such as flat panel display, liquid crystal display (LCD) or 3D display, through the solder balls **111**Z. The element in FIG. **38**D indicated by a same reference number as indicates the element in FIGS. **37**A and **37**D has a same material and spec as the element illustrated in FIGS. **37**A and **37**D.

[1067] The chip **313** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D can be a central-processing-unit (CPU) chip designed by x86 architecture, a central-processing-unit (CPU) chip designed by non x86 architectures, such as ARM, Strong ARM or MIPs, a baseband chip, a graphics-processing-unit (GPU) chip, a digital-signal-processing (DSP) chip, a wireless local area network (WLAN) chip, a global-positioning-system (GPS) chip, a bluetooth chip, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any baseband circuit block, a system-on chip (SOC) including a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any graphics-processing-unit (GPU) circuit block, a system-on chip (SOC) including a baseband circuit block, a graphics-processing-unit (GPU) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any wireless local area network (WLAN) circuit block, a system-on chip (SOC) including a baseband circuit block and a wireless local area network (WLAN) circuit block, but not including any graphics-processing-unit (GPU) circuit block and any central-processing-unit (CPU) circuit block, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block and a wireless local area network (WLAN) circuit block, but not including any baseband circuit block and any central-processing-unit (CPU) circuit block, or a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures. Alternatively, the chip **313** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D can be a chip including a central-

processing-unit (CPU) circuit block, a bluetooth circuit block, a global-positioning-system (GPS) circuit block, a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, and/or a wireless local area network (WLAN) circuit block. The chip **313**, graphics-processing-unit (GPU) chip, or the graphics-processing-unit (GPU) circuit block in the chip **313** can be designed for 2D or 3D video display, and can be connected to a 3D video display, such as 3D television (3D TV), or a 3D video game player through the microbumps **317**, the cache memory chip **311**, metal traces of the substrate **301** and the connector **307**, as shown in FIG. **37**A, **37**B, **37**C or **37**D, or through the microbumps **317**, the cache memory chip **311**, metal traces of the BGA substrate **302** and the solder balls **111***z*, as shown in FIG. **38**A, **38**B, **38**C or **38**D.

[1068] Referring to FIG. **41**, the RF module **325** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D can be replaced with a radio frequency (RF) module **325** shown in FIG. **41**. The RF module **325** is designed as a quad flat no-lead (QFN) package, and includes a lead frame with a die paddle **580***a* and leads **580***b*, a radio frequency (RF) chip **328***a* attached to the die paddle **580***a* by an adhesive material **581***a* of silver epoxy, polyimide or acrylic, a radio frequency (RF) chip **328***b* attached to the RF chip **328***a* by an adhesive material **581***b* of silver epoxy, polyimide or acrylic, multiple wire-bonded wires **119***c*, such as gold wires or copper wires, connecting the RF chips **328***a* and **328***b* to the leads **580***b*, and an encapsulation material **582** of epoxy or polyimide containing carbon or glass filler formed on the lead frame and at side-walls of the RF chips **328***a* and **328***b*, encapsulating the wire-bonded wires **119***c*. The leads **580***b* are arranged around the periphery of the die paddle **580***a*. Both of the RF chips **328***a* and **328***b* may include a radio frequency (RF) power amplifier, a radio frequency (RF) transceiver, a radio frequency (RF) driver amplifier, a balun circuit, a surface acoustic wave (SAW) filter, a filter, a coupler, and/or an isolator. The RF module **325** can be provided on and connected to the back side of the substrate **301** or **302** through multiple solder balls **111***m* containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. Alternatively, the RF module **325** can be provided on and connected to the top side of the substrate **301** or **302** through the solder balls **111** m. The solder balls **11 1***m* are formed between the leads **580***b* and the substrate **301** or **302**. The RF module **325** is used for transmitting or receiving RF (voice and/or data) signals for Wireless LAN (WLAN) communication and/or mobile phone communication, such as 3G CDMA (Code Division Multiple Access) or TDMA GSM (Time Division Multiple Access Global System for Mobile communication).

[1069] FIG. **39**A is an example of a circuit diagram showing interface circuits of the cache memory chip **311** and the chip **313** shown in FIG. **37**A, **37**B, **38**A or **38**B. The cache memory chip **311** includes two inter-chip circuits **20***a* and **20***b*, two internal circuits **20***c* and **20***d*, two off-chip circuits **40***a* and **40***b*, and two testing interface circuits **333***a* and **333***b*. The chip **313** includes two inter-chip circuits **20***e* and **20***f*, two internal circuits **20***g* and **20***h*, two off-chip circuits **40***c* and **40***d*, and two testing interface circuits **333***c* and **333***d*. The cache memory chip **311** is connected to the chip **313** through the microbumps **317** and to the substrate **301** or the BGA substrate **302** through the metal bumps or pillars **27**.

[1070] Referring to FIG. **39**A, the inter-chip circuit **20***a* of the cache memory chip **311** includes an inter-chip buffer **701***a* and an inter-chip ESD (electro static discharge) circuit **701***b*. The inter-chip buffer **701***a* has a first node FN**1** and a second node SN**1**, and the inter-chip ESD circuit **701***b* has a node En connected to the first node FN**1**. The inter-chip buffer **701***a* can be an inter-chip receiver which can be an inverter composed of an NMOS transistor **751***a* and a PMOS transistor **751***b*, and the gates of the NMOS transistor **751***a* and the PMOS transistor **751***b* serve as an input node that is the first node FN**1** of the inter-chip buffer **701***a*, and the drains of the NMOS transistor **751***a* and the PMOS transistor **751***b* serve as an output node that is the second node SN**1** of the inter-chip buffer **701***a*.

[1071] [**001065**] Alternatively, the inter-chip buffer **701***a* can be a multi-stage cascade inter-chip receiver including several stages of inverters. For example, referring to FIG. **39**B, the inter-chip buffer **701***a* can be a two-stage cascade inter-chip receiver. The first stage **424***a* of the two-stage cascade inter-chip receiver is an inverter composed of the NMOS transistor **751** a and the PMOS transistor **751***b*, and the second stage **424***b* (the last stage) of the two-stage cascade inter-chip receiver is also an inverter except that it is formed by a suitable process or processes, e.g., by a larger size of an NMOS transistor **751***c* and a PMOS transistor **751***d*. The gates of the NMOS transistor **751***a* and the PMOS transistor **751***b* serve as an input node that is the first node FN**1** of the inter-chip buffer **701***a*. The drains of the NMOS transistor **751***c* and the PMOS transistor **751***d* serve as an output node that is the second node SN**1** of the inter-chip buffer **701***a*. The drains of the NMOS transistor **751***a* and the PMOS transistor **751***b* are connected to the gates of the NMOS transistor **751***c* and the PMOS transistor **751***d*.

[1072] Referring to FIG. **39**A, the inter-chip circuit **20***b* of the cache memory chip **311** includes an inter-chip buffer **702***a* and an inter-chip ESD (electro static discharge) circuit **702***b*. The inter-chip buffer **702***a* has a first node FN**2** and a second node SN**2**, and the inter-chip ESD circuit **702***b* has a node En connected to the second node SN**2**. The inter-chip buffer **702***a* can be an inter-chip driver which can be an inverter composed of an NMOS transistor **752***a* and a PMOS transistor **752***b*, and the gates of the NMOS transistor **752***a* and the PMOS transistor **752***b* serve as an input node that is the first node FN**2** of the inter-chip buffer **702***a*, and the drains of the NMOS transistor **752***a* and the PMOS transistor **752***b* serve as an output node that is the second node SN**2** of the inter-chip buffer **702***a*.

[1073] Alternatively, the inter-chip buffer **702***a* can be a multi-stage cascade inter-chip driver including several stages of inverters. For example, referring to FIG. **39**C, the inter-chip buffer **702***a* can be a two-stage cascade inter-chip driver. The first stage **425***a* of the two-stage cascade inter-chip driver is an inverter composed of an NMOS transistor **752***c* and a PMOS transistor **752***d*, and the second stage **425***b* (the last stage) of the two-stage cascade inter-chip driver is an inverter composed of the NMOS transistor **752***a* and the PMOS transistor **752***b*. The gates of the NMOS transistor **752***c* and the PMOS transistor **752***d* serve as an input node that is the first node FN**2** of the inter-chip buffer **702***a*. The drains of the NMOS transistor **752***a* and the PMOS transistor **752***b* serve as an output node that is the second node SN**2** of the inter-chip buffer **702***a*. The drains of the NMOS transistor **752***c* and the PMOS transistor **752***d* are connected to the gates of the NMOS transistor **752***a* and the PMOS transistor **752***b*.

[1074] Referring to FIG. **39**A, the inter-chip circuit **20***e* of the chip **313** includes an inter-chip buffer **703***a* and an inter-chip ESD (electro static discharge) circuit **703***b*. The inter-

chip buffer **703***a* has a first node FN**3** and a second node SN**3**, and the inter-chip ESD circuit **703***b* has a node En connected to the second node SN**3**. The inter-chip buffer **703***a* can be an inter-chip driver which can be an inverter composed of an NMOS transistor **753***a* and a PMOS transistor **753***b*, and the gates of the NMOS transistor **753***a* and the PMOS transistor **753***b* serve as an input node that is the first node FN**3** of the inter-chip buffer **703***a*, and the drains of the NMOS transistor **753***a* and the PMOS transistor **753***b* serve as an output node that is the second node SN**3** of the inter-chip buffer **703***a*.

[1075] Alternatively, the inter-chip buffer **703***a* can be a multi-stage cascade inter-chip driver including several stages of inverters. For example, referring to FIG. **39**D, the inter-chip buffer **703***a* can be a two-stage cascade inter-chip driver. The first stage **426***a* of the two-stage cascade inter-chip driver is an inverter composed of an NMOS transistor **753***c* and a PMOS transistor **753***d*, and the second stage **426***b* (the last stage) of the two-stage cascade inter-chip driver is an inverter composed of the NMOS transistor **753***a* and the PMOS transistor **753***b*. The gates of the NMOS transistor **753***c* and the PMOS transistor **753***d* serve as an input node that is the first node FN**3** of the inter-chip buffer **703***a*. The drains of the NMOS transistor **753***a* and the PMOS transistor **753***b* serve as an output node that is the second node SN**3** of the inter-chip buffer **703***a*. The drains of the NMOS transistor **753***c* and the PMOS transistor **753***d* are connected to the gates of the NMOS transistor **753***a* and the PMOS transistor **753***b*.

[1076] Referring to FIG. **39**A, the inter-chip circuit **20***f* of the chip **313** includes an inter-chip buffer **704***a* and an inter-chip ESD (electro static discharge) circuit **704***b*. The inter-chip buffer **704***a* has a first node FN**4** and a second node SN**4**, and the inter-chip ESD circuit **704***b* has a node En connected to the first node FN**4**. The inter-chip buffer **704***a* can be an inter-chip receiver which can be an inverter composed of an NMOS transistor **754***a* and a PMOS transistor **754***b*, and the gates of the NMOS transistor **754***a* and the PMOS transistor **754***b* serve as an input node that is the first node FN**4** of the inter-chip buffer **704***a*, and the drains of the NMOS transistor **754***a* and the PMOS transistor **754***b* serve as an output node that is the second node SN**4** of the inter-chip buffer **704***a*.

[1077] Alternatively, the inter-chip buffer **704***a* can be a multi-stage cascade inter-chip receiver including several stages of inverters. For example, referring to FIG. **39**E, the inter-chip buffer **704***a* can be a two-stage cascade inter-chip receiver. The first stage **427***a* of the two-stage cascade inter-chip receiver is an inverter composed of the NMOS transistor **754***a* and the PMOS transistor **754***b*, and the second stage **427***b* (the last stage) of the two-stage cascade inter-chip receiver is an inverter composed of an NMOS transistor **754***c* and a PMOS transistor **754***d*. The gates of the NMOS transistor **754***a* and the PMOS transistor **754***b* serve as an input node that is the first node FN**4** of the inter-chip buffer **704***a*. The drains of the NMOS transistor **754***c* and the PMOS transistor **754***d* serve as an output node that is the second node SN**4** of the inter-chip buffer **704***a*. The drains of the NMOS transistor **754***a* and the PMOS transistor **754***b* are connected to the gates of the NMOS transistor **754***c* and the PMOS transistor **754***d*.

[1078] Referring to FIG. **39**A, the off-chip circuit **40***a* of the cache memory chip **311** includes an off-chip buffer **42***a* and an off-chip ESD (electro static discharge) circuit **43***a*. The off-chip buffer **42***a* has a first node FN**5** and a second node SN**5**, and the off-chip ESD circuit **43***a* has a node En connected to the first node FN**5**. The off-chip buffer **42***a* can be an off-chip receiver which can be an inverter composed of an NMOS transistor **4205** and a PMOS transistor **4206**, and the gates of the NMOS transistor **4205** and the PMOS transistor **4206** serve as an input node that is the first node FN**5** of the off-chip buffer **42***a*, and the drains of the NMOS transistor **4205** and the PMOS transistor **4206** serve as an output node that is the second node SN**5** of the off-chip buffer **42***a*.

[1079] Alternatively, the off-chip buffer **42***a* can be a multi-stage cascade off-chip receiver including several stages of inverters. For example, the off-chip buffer **42***a* can be a two-stage cascade off-chip receiver **422** shown in FIG. **11**B. The first stage **422'** of the two-stage cascade off-chip receiver **422** shown in FIG. **11**B is an inverter composed of the NMOS transistor **4205** and the PMOS transistor **4206**, and the second stage **422"** (the last stage) of the two-stage cascade off-chip receiver **422** shown in FIG. **11** B is also an inverter except that it is formed by a suitable process or processes, e.g., by a larger size of the NMOS transistor **4207** and the PMOS transistor **4208**. In FIG. **11**B, the input node E, served by the gates of the NMOS transistor **4205** and the PMOS transistor **4206**, can be the first node FN**5** of the off-chip buffer **42***a* shown in FIG. **39**A, and the output node F, served by the drains of the NMOS transistor **4207** and the PMOS transistor **4208**, can be the second node SN**5** of the off-chip buffer **42***a* shown in FIG. **39**A.

[1080] Referring to FIG. **39**A, the off-chip circuit **40***b* of the cache memory chip **311** includes an off-chip buffer **42***b* and an off-chip ESD (electro static discharge) circuit **43***b*. The off-chip buffer **42***b* has a first node FN**6** and a second node SN**6**, and the off-chip ESD circuit **43***b* has a node En connected to the second node SN**6**. The off-chip buffer **42***b* can be an off-chip driver which can be an inverter composed of an NMOS transistor **4203** and a PMOS transistor **4204**, and the gates of the NMOS transistor **4203** and the PMOS transistor **4204** serve as an input node that is the first node FN**6** of the off-chip buffer **42***b*, and the drains of the NMOS transistor **4203** and the PMOS transistor **4204** serve as an output node that is the second node SN**6** of the off-chip buffer **42***b*.

[1081] Alternatively, the off-chip buffer **42***b* can be a multi-stage cascade off-chip driver including several stages of inverters. For example, the off-chip buffer **42***b* can be a two-stage cascade off-chip driver **421** shown in FIG. **11**A. The first stage **421'** of the two-stage cascade inter-chip driver **421** shown in FIG. **11**A is an inverter composed of the NMOS transistor **4201** and the PMOS transistor **4202**, and the second stage **421"** (the last stage) of the two-stage cascade inter-chip driver **421** shown in FIG. **11**A is also an inverter except that it is formed by a suitable process or processes, e.g., by a larger size of the NMOS transistor **4203** and the PMOS transistor **4204**. In FIG. **11**A, the input node F, served by the gates of the NMOS transistor **4201** and the PMOS transistor **4202**, can be the first node FN**6** of the off-chip buffer **42***b* shown in FIG. **39**A, and the output node E, served by the drains of the NMOS transistor **4203** and the PMOS transistor **4204**, can be the second node SN**6** of the off-chip buffer **42***b* shown in FIG. **39**A.

[1082] Referring to FIG. **39**A, the off-chip circuit **40***c* of the chip **313** includes an off-chip buffer **42***c* and an off-chip ESD (electro static discharge) circuit **43***c*. The off-chip buffer **42***c* has a first node FN**7** and a second node SN**7**, and the off-chip ESD circuit **43***c* has a node En connected to the second node SN**7**. The off-chip buffer **42***c* can be an off-chip driver which can be an inverter composed of an NMOS transistor **4203***a* and a PMOS transistor **4204***a*, and the gates of the NMOS

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transistor **4203***a* and the PMOS transistor **4204***a* serve as an input node that is the first node FN**7** of the off-chip buffer **42***c*, and the drains of the NMOS transistor **4203***a* and the PMOS transistor **4204***a* serve as an output node that is the second node SN**7** of the off-chip buffer **42***c*.

[1083] Alternatively, the off-chip buffer **42***c* can be a multi-stage cascade off-chip driver including several stages of inverters. For example, referring to FIG. **39**F, the off-chip buffer **42***c* can be a two-stage cascade off-chip driver. The first stage **427***a* of the two-stage cascade off-chip driver is an inverter composed of an NMOS transistor **4201** a and a PMOS transistor **4202***a*, and the second stage **427***b* (the last stage) of the two-stage cascade off-chip driver is also an inverter except that it is formed by a suitable process or processes, e.g., by a larger size of the NMOS transistor **4203***a* and the PMOS transistor **4204***a*. The gates of the NMOS transistor **4201** a and the PMOS transistor **4202***a* serve as an input node that is the first node FN**7** of the off-chip buffer **42***c*. The drains of the NMOS transistor **4203***a* and the PMOS transistor **4204***a* serve as an output node that is the second node SN**7** of the off-chip buffer **42***c*. The drains of the NMOS transistor **4201***a* and the PMOS transistor **4202***a* are connected to the gates of the NMOS transistor **4203***a* and the PMOS transistor **4204***a*.

[1084] Referring to FIG. **39**A, the off-chip circuit **40***d* of the chip **313** includes an off-chip buffer **42***d* and an off-chip ESD (electro static discharge) circuit **43***d*. The off-chip buffer **42***d* has a first node FN**8** and a second node SN**8**, and the off-chip ESD circuit **43***d* has a node En connected to the first node FN**8**. The off-chip buffer **42***d* can be an off-chip receiver which can be an inverter composed of an NMOS transistor **4205***a* and a PMOS transistor **4206***a*, and the gates of the NMOS transistor **4205***a* and the PMOS transistor **4206***a* serve as an input node that is the first node FN**8** of the off-chip buffer **42***d*, and the drains of the NMOS transistor **4205***a* and the PMOS transistor **4206***a* serve as an output node that is the second node SN**8** of the off-chip buffer **42***d*.

[1085] Alternatively, the off-chip buffer **42***d* can be a multi-stage cascade off-chip receiver including several stages of inverters. For example, referring to FIG. **39**G, the off-chip buffer **42***d* can be a two-stage cascade off-chip receiver. The first stage **428***a* of the two-stage cascade off-chip receiver is an inverter composed of the NMOS transistor **4205***a* and the PMOS transistor **4206***a*, and the second stage **428***b* (the last stage) of the two-stage cascade off-chip receiver is also an inverter except that it is formed by a suitable process or processes, e.g., by a larger size of the NMOS transistor **4207***a* and the PMOS transistor **4208***a*. The gates of the NMOS transistor **4205***a* and the PMOS transistor **4206***a* serve as an input node that is the first node FN**8** of the off-chip buffer **42***d*. The drains of the NMOS transistor **4207***a* and the PMOS transistor **4208***a* serve as an output node that is the second node SN**8** of the off-chip buffer **42***d*. The drains of the NMOS transistor **4205***a* and the PMOS transistor **4206***a* are connected to the gates of the NMOS transistor **4207***a* and the PMOS transistor **4208***a*.

[1086] FIG. **39**H is another example of the circuit diagram showing interface circuits of the cache memory chip **311** and the chip **313** shown in FIG. **37**A, **37**B, **38**A or **38**B. The circuit diagram shown in FIG. **39**H is similar to that shown in FIG. **39**A except that the inter-chip buffers **701***a*, **702***a*, **703***a* and **704***a* are designed with inter-chip tri-state buffers each including a tri-state driver and a tri-state receiver, instead of the inter-chip receivers and drivers, and the off-chip buffers **42***a*, **42***b*, **42***c* and **42***d* are designed with off-chip tri-state buffers each including a tri-state driver and a tri-state receiver, instead of the off-chip receivers and drivers. In FIG. **39**H, the inter-chip buffer **701***a* of the cache memory chip **311** can be an inter-chip tri-state buffer having a first I/O (input/output) node serving as the first node FN**1** of the inter-chip buffer **701***a*, and having a second I/O node serving as the second node SN**1** of the inter-chip buffer **701***a*. The inter-chip buffer **702***a* of the cache memory chip **311** can be an inter-chip tri-state buffer having a first I/O node serving as the first node FN**2** of the inter-chip buffer **702***a*, and having a second I/O node serving as the second node SN**2** of the inter-chip buffer **702***a*. The inter-chip buffer **703***a* of the chip **313** can be an inter-chip tri-state buffer having a first I/O node serving as the first node FN**3** of the inter-chip buffer **703***a*, and having a second I/O node serving as the second node SN**3** of the inter-chip buffer **703***a*. The inter-chip buffer **704***a* of the chip **313** can be an inter-chip tri-state buffer having a first I/O node serving as the first node FN**4** of the inter-chip buffer **704***a*, and having a second I/O node serving as the second node SN**4** of the inter-chip buffer **704***a*. The off-chip buffer **42***a* of the cache memory chip **311** can be an off-chip tri-state buffer having a first I/O node serving as the first node FN**5** of the off-chip buffer **42***a*, and having a second I/O node serving as the second node SN**5** of the off-chip buffer **42***a*. The off-chip buffer **42***b* of the cache memory chip **311** can be an off-chip tri-state buffer having a first I/O node serving as the first node FN**6** of the off-chip buffer **42***b*, and having a second I/O node serving as the second node SN**6** of the off-chip buffer **42***b*. The off-chip buffer **42***c* of the chip **313** can be an off-chip tri-state buffer having a first I/O node serving as the first node FN**7** of the off-chip buffer **42***c*, and having a second I/O node serving as the second node SN**7** of the off-chip buffer **42***c*. The off-chip buffer **42***d* of the chip **313** can be an off-chip tri-state buffer having a first I/O node serving as the first node FN**8** of the off-chip buffer **42***d*, and having a second I/O node serving as the second node SN**8** of the off-chip buffer **42***d*.

[1087] Referring to FIGS. **39**A and **39**H, each of the internal circuits **20***c*, **20***d*, **20***g* and **20***h* can be a NOR gate, a NAND gate, an AND gate, an OR gate, an operational amplifier, a flash memory cell, a static-random-access-memory (SRAM) cell, a dynamic-random-access-memory (DRAM) cell, a non-volatile memory cell, an erasable programmable read-only memory (EPROM) cell, a read-only memory (ROM) cell, a magnetic random access memory (MRAM) cell, a sense amplifier, an analog-to-digital (A/D) converter, a digital-to-analog (D/A) converter, an inverter, an adder, a multiplexer, a diplexer, a multiplier, a complementary-metal-oxide-semiconductor (CMOS) device, a bi-polar CMOS device, a bipolar circuit or an analog circuit. Each of the internal circuits **20***c*, **20***d*, **20***g*and **20***h* may include a NMOS transistor having a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 and 20, ranging from, e.g., about 0.1 and 10 or ranging from, e.g., about 0.2 and 2. Alternatively, each of the internal circuits **20***c*, **20***d*, **20***g* and **20***h* may include a PMOS transistor having a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 and 40, ranging from, e.g., about 0.2 and 40 or ranging from, e.g., about 0.4 and 4. Each of the inter-chip ESD circuits **701***b*, **702***b*, **703***b* and **704***b* and each of the off-chip ESD circuits **43***a*, **43***b*, **43***c* and **43***d* may include one or more ESD (electro static discharge) units each composed of two reverse-biased diodes or of a PMOS transistor and an NMOS transistor.

[1088] The first node FN**1** of the inter-chip buffer **701***a* can be connected to the node En of the inter-chip ESD circuit **701***b*, to a first terminal F**1** of the testing interface circuit **333***a* through a metal interconnect line **640***b* of the cache memory chip **311**, to the left metal pad **600***b*, including aluminum or electroplated copper, of the cache memory chip **311** through the metal interconnect line **640***b*, and to the left microbump **317** through the metal interconnect line **640***b* and the left metal pad **600***b*. The second node SNI of the inter-chip buffer **701***a* can be connected to the internal circuit **20***c* through a metal interconnect line **640***a* of the cache memory chip **311**.

[1089] The first node FN**2** of the inter-chip buffer **702***a* can be connected to the internal circuit **20***d* through a metal interconnect line **640***c* of the cache memory chip **311**. The second node SN**2** of the inter-chip buffer **702***a* can be connected to the node En of the inter-chip ESD circuit **702***b*, to a first terminal F**2** of the testing interface circuit **333***b* through a metal interconnect line **640***d* of the cache memory chip **311**, to the right metal pad **600***b*, including aluminum or electroplated copper, of the cache memory chip **311** through the metal interconnect line **640***d*, and to the right microbump **317** through the metal interconnect line **640***d* and the right metal pad **600***b*.

[1090] The first node FN**3** of the inter-chip buffer **703***a* can be connected to the internal circuit **20***g* through a metal interconnect line **640***e* of the chip **313**. The second node SN**3** of the inter-chip buffer **703***a* can be connected to the node En of the inter-chip ESD circuit **703***b*, to a first terminal F**3** of the testing interface circuit **333***c* through a metal interconnect line **640***f* of the chip **313**, to the left metal pad **600***c*, including aluminum or electroplated copper, of the chip **313** through the metal interconnect line **640***f*, to the left microbump **317** through the metal interconnect line **640***f* and the left metal pad **600***c*, and to the first node FN**1** of the inter-chip buffer **701***a* of the cache memory chip **311** through the metal interconnect line **640***f* of the chip **313**, the left metal pad **600***c* of the chip **313**, the left microbump **317**, the left metal pad **600***b* of the cache memory chip **311**, and the metal interconnect line **640***b* of the cache memory chip **311**.

[1091] The first node FN**4** of the inter-chip buffer **704***a* can be connected to the node En of the inter-chip ESD circuit **704***b*, to a first terminal F**4** of the testing interface circuit **333***d* through a metal interconnect line **640***h* of the chip **313**, to the right metal pad **600***c*, including aluminum or electroplated copper, of the chip **313** through the metal interconnect line **640***h*, to the right microbump **317** through the metal interconnect line **640***h* and the right metal pad **600***c*, and to the second node SN**2** of the inter-chip buffer **7024** of the cache memory chip **311** through the metal interconnect line **640***h* of the chip **313**, the right metal pad **600***c* of the chip **313**, the right microbump **317**, the right metal pad **600***b* of the cache memory chip **311**, and the metal interconnect line **640***d* of the cache memory chip **311**. The second node SN**4** of the inter-chip buffer **704***a* can be connected to the internal circuit **20***h* through a metal interconnect line **640***g* of the chip **313**.

[1092] The first node FN**5** of the off-chip buffer **42***a* can be connected to the node En of the off-chip ESD circuit **43***a*, to the testing metal pad **600***t*, including aluminum or electroplated copper, of the cache memory chip **311** through a metal interconnect line **640***j* of the cache memory chip **311**, to a metal pad **886** of the cache memory chip **311** through the metal interconnect line **640***j*, and to the left metal bump or pillar **27** through the metal interconnect line **640***j* and the metal pad **886**. The left metal bump or pillar **27** can be provided on and connected to the substrate **301** shown in FIG. **37**A or **37**B or to the BGA substrate **302** shown in FIG. **38**A or **38**B, and the first node FN**5** of the off-chip buffer **42***a* can be connected to the substrate **301** or the BGA substrate **302** through the metal interconnect line **640***j*, the metal pad **886** and the left metal bump or pillar **27**. The second node SN**5** of the off-chip buffer **42***a* can be connected to a second terminal S**1** of the testing interface circuit **333***a* through a metal interconnect line **640***i* of the cache memory chip **311**.

[1093] The first node FN**6** of the off-chip buffer **42***b* can be connected to a second terminal S**2** of the testing interface circuit **333***b* through a metal interconnect line **640***k* of the cache memory chip **311**. The second node SN**6** of the off-chip buffer **42***b* can be connected to the off-chip ESD circuit **43***b*, to the testing metal pad **600***s*, including aluminum or electroplated copper, of the cache memory chip **311** through a metal interconnect line **640***m* of the cache memory chip **311**, to a metal pad **887** of the cache memory chip **311** through the metal interconnect line **640***m*, and to the right metal bump or pillar **27** through the metal interconnect line **640***m* and the metal pad **887**. The right metal bump or pillar **27** can be provided on and connected to the substrate **301** shown in FIG. **37**A or **37**B or to the BGA substrate **302** shown in FIG. **38**A or **38**B, and the second node SN**6** of the off-chip buffer **42***b* can be connected to the substrate **301** or the BGA substrate **302** through the metal interconnect line **640***m*, the metal pad **887** and the right metal bump or pillar **27**.

[1094] The first node FN**7** of the off-chip buffer **42***c* can be connected to a second terminal S**3** of the testing interface circuit **333***c* through a metal interconnect line **640***n* of the chip **313**. The second node SN**7** of the off-chip buffer **42***c* can be connected to the off-chip ESD circuit **43***c*, and to the testing metal pad **600***w*, including aluminum or electroplated copper, of the chip **313** through a metal interconnect line **640***p* of the chip **313**.

[1095] The first node FN**8** of the off-chip buffer **42***d* can be connected to the off-chip ESD circuit **43***d*, and to the testing metal pad **600***x*, including aluminum or electroplated copper, of the chip **313** through a metal interconnect line **640***r* of the chip **313**. The second node SN**8** of the off-chip buffer **42***d* can be connected to a second terminal S**4** of the testing interface circuit **333***d* through a metal interconnect line **640***q* of the chip **313**.

[1096] FIG. **391** is an example of a circuit diagram showing interface circuits of the cache memory chip **311** and the chip **313** shown in FIG. **37**C, **37**D, **38**C or **38**D. The circuit diagram shown in FIG. **391** is similar to that shown in FIG. **39**A except that the cache memory chip **311** is connected to the substrate **301** or the BGA substrate **302** through the wirebonded wires **119***c* instead of the metal bumps or pillars **27**. The element in FIG. **391** indicated by a same reference number as indicates the element in FIG. **39**A has a same material and spec as the element illustrated in FIG. **39**A.

[1097] FIG. **39**J is another example of the circuit diagram showing interface circuits of the cache memory chip **311** and the chip **313** shown in FIG. **37**C, **37**D, **38**C or **38**D. The circuit diagram shown in FIG. **39**J is similar to that shown in FIG. **39**H except that the cache memory chip **311** is connected to the substrate **301** or the BGA substrate **302** through the wirebonded wires **119***c* instead of the metal bumps or pillars **27**. The element in FIG. **39**J indicated by a same reference number as indicates the element in FIG. **39**H has a same material and spec as the element illustrated in FIG. **39**H.

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[1098] In FIGS. **37**A-**37**D, **38**A-**38**D, **39**A, and **39**H-**39**J, the cache memory chip **311** may have a memory size larger than 10 megabytes, such as between 10 megabytes and 32 gigabytes, and preferably between 100 megabytes and 4 gigabytes. For example, the cache memory chip **311** can be a dynamic-random-access-memory (DRAM) chip, a static-random-access-memory (SRAM) chip or a synchronous-dynamic-random-access-memory (SDRAM) chip with a memory size larger than **10** megabytes, such as between 10 megabytes and 32 gigabytes, and preferably between 100 megabytes and 4 gigabytes. Very parallel communication is used between the chip **313** and the cache memory chip **311**. The data bit width between the chip **313** and the cache memory chip **311** is equal to or more than 512, and preferably equal to or more than 1024. The cache memory chip **311** has the testing metal pads **600***s* and **600***t* used for testing the cache memory chip **311**.

[1099] In FIGS. **37**A, **37**D, **38**A and **38**D, since two cache memory chips **311** and **321** provided on two opposite sides of the chip **313** respectively, the processor unit **303** has double bit width between the chip **313** and a cache memory provided by the cache memory chips **311** and **321**. The cache memory chip **321** may have a memory size larger than 10 megabytes, such as between 10 megabytes and 32 gigabytes, and preferably between 100 megabytes and 4 gigabytes. For example, the cache memory chip **321** can be a dynamic-random-access-memory (DRAM) chip, a static-random-access-memory (SRAM) chip or a synchronous-dynamic-random-access-memory (SDRAM) chip with a memory size larger than 10 megabytes, such as between 10 megabytes and 32 gigabytes, and preferably between 100 megabytes and 4 gigabytes. Very parallel communication is used between the chip **313** and the cache memory chip **321**. The data bit width between the chip **313** and the cache memory chip **321** is equal to or more than 512, and preferably equal to or more than 1024. The cache memory chip **321** has two testing metal pads **600***y* and **600***z* used for testing the cache memory chip **321**.

[1100] Referring to FIG. **39**A and FIGS. **39**H-**39**J, very small load is between the chip **313** and the cache memory chip **311**. The small inter-chip buffer **701***a* or **702***a*, such as inter-chip driver, inter-chip receiver or inter-chip tri-state buffer, is designed just like an internal buffer, such as internal driver, internal receiver or internal tri-state buffer, respectively, used for long interconnection within the cache memory chip **311**, that is, the long interconnection connects multiple transistors in long distance within the cache memory chip **311**. The small inter-chip buffer **703***a* or **704***a*, such as inter-chip driver, inter-chip receiver or inter-chip tri-state buffer, is designed just like an internal buffer, such as internal driver, internal receiver or internal tri-state buffer, respectively, used for long interconnection within the chip **313**, that is, the long interconnection connects multiple transistors in long distance within the chip **313**. The small inter-chip buffers **701***a*, **702***a*, **703***a* and **704***a* are designed on both the chip **313** and the cache memory chip **311** for a signal, clock, power or ground connection between the chip **313** and the cache memory chip **311**. The number of inter-chip buffers including the inter-chip buffers **701***a* and **702***a* on the cache memory chip **311** is equal to or more than 512, and preferably equal to or more than 1024. The number of inter-chip buffers including the inter-chip buffers **703***a* and **704***a* on the chip **313** is equal to or more than **512**, and preferably equal to or more than 1024.

[1101] The large off-chip buffers **42***a*, **42***b*, **42***c* and **42***d*, such as off-chip drivers, off-chip receivers or off-chip tri-sate buffers, are designed on both the chip **313** and the cache memory chip **311** for circuit testing and/or for signal, clock, power or ground connection to external circuits, such as the substrate **301** or the BGA substrate **302**, and the external circuits are circuits not on the chip **313** or the cache memory chip **311**, and the circuit testing is either (i) the wafer level testing performed before the chip **311** or **313** is sawed or diced apart from a wafer, or (ii) the package level testing (the final testing) after the chips **311** and **313** are joined with each other.

[1102] The testing interface circuits **333***a*, **333***b*, **333***c* and **333***d* are designed on both the chip **313** and the cache memory chip **311**. The output capacitance at the first terminal F**1** or F**4** of the testing interface circuit **333***a* or **333***d* shown in FIG. **39**A or **391** as seen from the inter-chip buffer **701***a* or **704***a* is smaller than 2 pF, exemplary smaller than 1 pF or smaller than 0.2 pF. The output loading capacitance of the first terminal F**1** or F**4** of the testing interface circuit **333***a* or **333***d* shown in FIG. **39**A or **391** is smaller than 2 pF, exemplary smaller than 1 pF or smaller than 0.2 pF. The input capacitance at the first terminal F**2** or F**3** of the testing interface circuit **333***b* or **333***c* shown in FIG. **39**A or **391** as seen from the inter-chip buffer **702***a* or **703***a* is smaller than 2 pF, exemplary smaller than 1 pF or smaller than 0.2 pF. The input loading capacitance of the first terminal F**2** or F**3** of the testing interface circuit **333***b* or **333***c* shown in FIG. **39**A or **391** is smaller than 2 pF, exemplary smaller than 1 pF or smaller than 0.2 pF. The input or output capacitance at the first terminal F**1**, F**2**, F**3** or F**4** of the testing interface circuit **333***a*, **333***b*, **333***c* or **333***d* shown in FIG. **39**H or **39**J as seen from the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* is smaller than 2 pF, exemplary smaller than 1 pF or smaller than 0.2 pF. The input or output loading capacitance of the first terminal F**1**, F**2**, F**3** or F**4** of the testing interface circuit **333***a*, **333***b*, **333***c* or **333***d* shown in FIG. **39**H or **39**J is smaller than 2 pF, exemplary smaller than 1 pF or smaller than 0.2 pF. Each of the test interface circuits **333***a*, **333***b*, **333***c* and **333***d* can be a scan test circuit, and the scan test circuit can be performed at the wafer level testing before the chip **311** or **313** is sawed or diced apart from a wafer or at the package level testing (the final testing) after the chips **311** and **313** are joined with each other, and the scan test circuit is used to test flip flops by input the scan-in signal or output the scan-out signal.

[1103] The small inter-chip ESD circuits **701***b*, **702***b*, **703***b* and **704***b* are used for the small inter-chip buffers **701***a*, **702***a*, **703***a* and **704***a* between the chip **313** and the cache memory chip **311** for electrostatic charge protection during the chip packaging or assembly manufacturing process. Alternatively, no ESD circuit can be required for the small inter-chip buffers **701***a*, **702***a*, **703***a* and **704***a* between the chip **313** and the cache memory chip **311**, that is, the inter-chip ESD circuits **701***b*, **702***b*, **703***b* and **704***b* can be omitted. In other words, there is no ESD circuit connected to the metal interconnect lines **640***b*, **640***d*, **640***f* and **640***h*.

[1104] The large off-chip ESD circuits **43***a*, **43***b*, **43***c* and **43***d* required for the large off-chip buffers **42***a*, **42***b*, **42***c*, and **42***d* are designed on both the chip **313** and the cache memory chip **311** for the circuit testing and/or for signal, clock, power or ground connection to external circuits, such as the substrate **301** or the BGA substrate **302**, and the external circuits are circuits not on the chip **313** and the cache memory chip **311**, and the circuit testing is either (i) the wafer level testing performed before the chip **311** or **313** is sawed or diced apart from a wafer, or (ii) the package level testing (the final testing) after the chips **311** and **313** are joined with each other. The

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large off-chip ESD circuits **43***a*, **43***b*, **43***c* and **43***d* are used for electrostatic charge protection during the circuit testing, such as the wafer level testing or the package level testing (the final testing).

[1105] The size of the inter-chip ESD circuit **701***b*, **702***b*, **703***b* or **704***b* can be defined as the loading or capacitance of the inter-chip ESD circuit **701***b*, **702***b*, **703***b* or **704***b*, and the size of the off-chip ESD circuit **43***a*, **43***b*, **43***c* or **43***d* can be defined as the loading or capacitance of the off-chip ESD circuit **43***a*, **43***b*, **43***c* or **43***d*. In a case, each of the small inter-chip ESD circuits **701***b*, **702***b*, **703***b* and **704***b* has a size (loading or capacitance) smaller than 2 pF (pico Farads), such as between 0.01 and 2 pF, exemplary smaller than 0.5 pF, such as between 0.01 and 0.5 pF, and each of the large off-chip ESD circuits **43***a*, **43***b*, **43***c* and **43***d* has a size (loading or capacitance) larger than 2 pF, such as between 2 and 100 pF, exemplary larger than 5 pF, such as between 5 and 100 pF. In another case, each of the small inter-chip ESD circuits **701***b*, **702***b*, **703***b* and **704***b* has a size (loading or capacitance) smaller than 1 pF, such as between 0.01 and 1 pF, and each of the large off-chip ESD circuits **43***a*, **43***b*, **43***c* and **43***d* has a size (loading or capacitance) larger than 1 pF, such as between 1 and 100 pF.

[1106] Alternatively, the size of the small inter-chip ESD circuit **701***b*, **702***b*, **703***b* or **704***b* or the size of the large off-chip ESD circuit **43***a*, **43***b*, **43***c* or **43***d* can be defined as below. An ESD (electro static discharge) circuit, such as the inter-chip ESD circuit **701***b*, **702***b*, **703***b* or **704***b* or the off-chip ESD circuit **43***a*, **43***b*, **43***c* or **43***d*, may include one or more ESD units, and each of the ESD units may include a P^+ active region and an N^+ active region connected to the P^+ active region and connected to an I/O (input/output) metal pad or testing metal pad of a chip, such as the metal pad **600***b*, **600***c*, **600***t*, **600***s*, **600***w* or **600***x* shown in FIG. **39**A, **39**H, **39**I or **39**J, and the area of the P^+ active region plus the area of the N^+ active region equals the active area of each of the ESD units. The total of the active areas of the ESD units equals the active area of the ESD circuit. If the ESD circuit is composed of only one ESD unit, the active area of the ESD circuit equals the active area of the only one ESD unit. If the ESD circuit is composed of multiple ESD units, the active area of the ESD circuit equals the total of the active areas of the ESD units connected in parallel. The active area of the ESD circuit can be used to define the size of the ESD circuit. FIGS. **40**A-**40**F show how to calculate the active area of an ESD unit of a chip and define the size of an ESD circuit composed of one or more the ESD units. Referring to FIG. **40**A, an electro static discharge (ESD) unit **743** of a chip can be composed of two reverse-biased diodes **4331** and **4332**. FIG. **40**C shows a cross-sectional view of the ESD unit **743** shown in FIG. **40**A, and FIG. **40**D is a top perspective view showing the topography of the ESD unit **743** derived from the top surface Z-Z' of a p-type silicon substrate **1** shown in FIG. **40**C. Referring to FIGS. **40**C and **40**D, the ESD unit **743** includes two P^+ active regions **757***a* and **757***b* and two N^+ active regions **758***a* and **758***b*. The P^+ active region **757***a* is in an N-well **755** in the p-type silicon substrate **1**, and the N^+ active region **758***a* is in the p-type silicon substrate **1**. The P^+ active region **757***a* is connected to an I/O metal pad or testing metal pad of the chip, such as the metal pad **600***b*, **600***t* or **600***s* of the cache memory chip **311** or metal pad **600***c*, **600***w* or **600***x* of the chip **313** shown in FIG. **39**A, **39**H, **39**I or **39**J, through a metal interconnect line **753***a* of the chip. The N^+ active region **758***a* is connected to the P^+ active region **757***a* and to the I/O metal pad or the testing metal pad of the chip through the metal interconnect line **753***a*. The metal interconnect line **753***a* includes a portion provided by multiple fine-line metal layers **60** over the p-type silicon substrate **1**, a first via plug **60'** formed on a contact region **754***a* of the P^+ active region **757***a*, and a second via plug **60'** formed on a contact region **754***b* of the N^+ active region **758***a*. The P^+ active region **757***b* is in the p-type silicon substrate **1**, and the N^+ active region **758***b* is in the N-well **755** in the p-type silicon substrate **1**. The P^+ active region **757***b* is connected to a ground bus through a metal interconnect line **753***b*, and the N^+ active region **758***b* is connected to a power bus through a metal interconnect line **735***c*. The metal interconnect line **753***b* contains a portion provided by the fine-line metal layers **60** over the p-type silicon substrate **1** and a via plug **60'** formed on a contact region **754***c* of the P^+ active region **757***b*. The metal interconnect line **753***c* contains a portion provided by the fine-line metal layers **60** over the p-type silicon substrate **1** and a via plug **60'** formed on a contact region **754***d* of the N^+ active region **758***b*.

[1107] Referring to FIG. **40**D, the P^+ active region **757***a*, connected to the I/O metal pad or testing metal pad of the chip, has an area AR**1**, from a top view, enclosed by a field oxide **752** in the p-type silicon substrate **1**. The N^+ active region **758***a*, connected to the I/O metal pad or testing metal pad of the chip, has an area AR**2**, from a top view, enclosed by the field oxide **752** in the p-type silicon substrate **1**. The active area of the ESD unit **743** equals the area AR**1** plus the area AR**2**.

[1108] Alternatively, referring to FIG. **40**B, the ESD unit **743** of the chip can be composed of a PMOS transistor **681** and an NMOS transistor **682**. FIG. **40**E shows a cross-sectional view of the ESD unit **743** shown in FIG. **40**B, and FIG. **40**F is a top perspective view showing the topography of the ESD unit **743** derived from the top surface Z-Z' of the p-type silicon substrate **1** shown in FIG. **40**E. Referring to FIGS. **40**B, **40**E and **40**F, the PMOS transistor **681** of the ESD unit **743** includes a gate **751***a* and two P^+ active regions **757***a* and **757***c* at two opposite sides of the gate **751***a*, and the NMOS transistor **682** of the ESD unit **743** includes a gate **751***b* and two N^+ active regions **758***a* and **758***c* at two opposite sides of the gate **751***b*. The P^+ active region **757***a* is in an N-well **755** in the p-type silicon substrate **1**, and the N^+ active region **758***a* is in the p-type silicon substrate **1**. The P^+ active region **757***a* is connected to an I/O metal pad or testing metal pad of the chip, such as the metal pad **600***b*, **600***t* or **600***s* of the cache memory chip **311** or metal pad **600***c*, **600***w* or **600***x* of the chip **313** shown in FIG. **39**A, **39**H, **39**I or **39**J, through a metal interconnect line **753***a* of the chip, and the N^+ active region **758***a* is connected to the P^+ active region **757***a* and to the I/O metal pad or the testing metal pad of the chip through the metal interconnect line **753***a*. The metal interconnect line **753***a* contains a portion provided by multiple fine-line metal layers **60** over the p-type silicon substrate **1**, a first via plug **60'** formed on a contact region **754***a* of the P^+ active region **757***a*, and a second via plug **60'** formed on a contact region **754***b* of the N^+ active region **758***a*. The P^+ active region **757***b* is in the p-type silicon substrate **1**, and the N^+ active region **758***b* is in the N-well **755** in the p-type silicon substrate **1**. The P^+ active region **757***c* is in the N-well **755** in the p-type silicon substrate **1**, and the N^+ active region **758***c* is in the p-type silicon substrate **1**. The N^+ active region **758***c* is connected to a ground bus of the chip through a metal interconnect line **753***b* of the chip and to the P^+ active region **757***b* through the

interconnect line **753***b*, and the P^+ active region **757***b* is connected to the ground bus through the metal interconnect line **753***b*. The P^+ active region **757***c* is connected to a power bus of the chip through a metal interconnect line **735***c* of the chip and to the N^+ active region **758***b* through the metal interconnect line **735***c*, and the N^+ active region **758***b* is connected to the power bus through the metal interconnect line **735***c*. The metal interconnect line **753***b* contains a portion provided by the fine-line metal layers **60** over the p-type silicon substrate **1**, a first via plug **60'** formed on a contact region **754***c* of the P^+ active region **757***b*, and a second via plug **60'** formed on a contact region **754***e* of the N^+ active region **758***c*. The metal interconnect line **753***c* contains a portion provided by the fine-line metal layers **60** over the p-type silicon substrate **1**, a first via plug **60'** formed on a contact region **754***d* of the N^+ active region **758***b*, and a second via plug **60'** formed on a contact region **754***f* of the P^+ active region **757***c*. The gate **751***a* has a contact region **754***g* connected to the power bus of the chip and to the contact regions **754***d* and **754***f* through the metal interconnect line **753***c*. The gate **751***b* has a contact region **754***h* connected to the ground bus of the chip and to the contact regions **754***c* and **754***e* through the metal interconnect line **753***b*.

[1109] Referring to FIG. **40**F, the P^+ active region **757***a*, connected to the I/O metal pad or testing metal pad of the chip, has an area AR**3**, from a top view, enclosed by the boundary defined by a sidewall **748** of the gate **751***a* and the border between a field oxide **752** and the P^+ active region **757***a*. The N^+ active region **758***a*, connected to the I/O metal pad or testing metal pad of the chip, has an area AR**4**, from a top view, enclosed by the boundary defined by a sidewall **749** of the gate **751***b* and the border between the field oxide **752** and the N^+ active region **758***a*. The active area of the ESD unit **743** equals the area AR**3** plus the area AR**4**.

[1110] Based on the previously described definition or calculation illustrated in FIGS. **40**A-**40**F, the active area of each of ESD units of an ESD circuit can be calculated, and the total of active areas of the ESD units equals the active area of the ESD circuit. If the ESD circuit is composed of only one ESD unit, the active area of the ESD circuit equals the active area of the only one ESD unit. If the ESD circuit is composed of multiple ESD units, the active area of the ESD circuit equals the total of the active areas of the ESD units connected in parallel.

[1111] Accordingly, the active area of each of the inter-chip ESD circuits **701***b*, **702***b*, **703***b* and **704***b* and the active area of each of the off-chip ESD circuits **43***a*, **43***b*, **43***c* and **43***d* can be calculated. For example, the small inter-chip ESD circuit **701***b*, **702***b*, **703***b* or **704***b* may have an active area smaller than 1300 square millimeters, such as between 6.5 and 1300 square millimeters, exemplary smaller than 325 square millimeters, such as between 6.5 and 325 square millimeters, and the large off-chip ESD circuit **43***a*, **43***b*, **43***c* or **43***d* may have an active area larger than 1300 square millimeters, such as between 1300 and 65000 square millimeters, exemplary larger than 3250 square millimeters, such as between 3250 and 65000 square millimeters. Alternatively, the small inter-chip ESD circuit **701***b*, **702***b*, **703***b* or **704***b* may have an active area smaller than 650 square millimeters, and the large off-chip ESD circuit **43***a*, **43***b*, **43***c* or **43***d* may have an active area larger than 650 square millimeters.

[1112] The size of the large off-chip ESD circuit **43***a* of the cache memory chip **311**, defined as the total of the active areas of the one or more ESD units in the large off-chip ESD circuit **43***a* or the loading or capacitance of the large off-chip ESD circuit **43***a*, can be larger than the size of the small inter-chip ESD circuit **701***b* of the cache memory chip **311**, defined as the total of the active areas of the one or more ESD units in the small inter-chip ESD circuit **701***b* or the loading or capacitance of the small inter-chip ESD circuit **701***b*, by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 50 times.

[1113] The size of the large off-chip ESD circuit **43***b* of the cache memory chip **311**, defined as the total of the active regions of the one or more ESD units in the large off-chip ESD circuit **43***b* or the loading or capacitance of the large off-chip ESD circuit **43***b*, can be larger than the size of the small inter-chip ESD circuit **702***b* of the cache memory chip **311**, defined as the total of the active regions of the one or more ESD units in the small inter-chip ESD circuit **702***b* or the loading or capacitance of the small inter-chip ESD circuit **702***b*, by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 50 times.

[1114] The size of the large off-chip ESD circuit **43***c* of the chip **313** defined as the total of the active regions of the one or more ESD units in the large off-chip ESD circuit **43***c* or the loading or capacitance of the large off-chip ESD circuit **43***c*, can be larger than the size of the small inter-chip ESD circuit **703***b* of the chip **313**, defined as the total of the active regions of the one or more ESD units in the small inter-chip ESD circuit **703***b* or the loading or capacitance of the small inter-chip ESD circuit **703***b*, by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 50 times.

[1115] The size of the large off-chip ESD circuit **43***d* of the chip **313** defined as the total of the active regions of the one or more ESD units in the large off-chip ESD circuit **43***d* or the loading or capacitance of the large off-chip ESD circuit **43***d*, can be larger than the size of the small inter-chip ESD circuit **704***b* of the chip **313**, defined as the total of the active regions of the one or more ESD units in the small inter-chip ESD circuit **704***b* or the loading or capacitance of the small inter-chip ESD circuit **704***b*, by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 50 times.

[1116] The size of the inter-chip buffer **702***a* or **703***a* shown in FIG. **39**A or **39**I can be characterized by the load or loading of the inter-chip buffer **702***a* or **703***a*. Referring to FIG. **39**A or **39**I, the load or loading of the inter-chip buffer **702***a* or **703***a* is total equivalent capacitance load of the inter-chip buffer **702***a* or **703***a*, and the inter-chip buffer **702***a* or **703***a* is designed with a certain size for driving the load or loading that equals a capacitance C_{a1} plus a capacitance C_{a2} plus a capacitance C_{a3} plus a capacitance C_{g1} plus a capacitance C_{g2} plus a capacitance C_{b1} plus a capacitance C_{b2} plus a capacitance C_{b3}. The capacitance C_{a1} is a capacitance of the metal interconnect line **640***d* or **640***f* between the inter-chip buffer **702***a* or **703***a* and the metal pad **600***b* or **600***c* on the chip **311** or **313**. The capacitance C_{a2} is a capacitance of the metal pad **600***b* or **600***c* corresponding to the inter-chip buffer **702***a* or **703***a* on the chip **311** or **313**. The capacitance C_{a3} is a parasitic capacitance correspondent to the inter-chip **702***a* or **703***a* on the chip **311** or **313**. The capacitance C_{g1} is a capacitance of the microbump **317**. The capacitance C_{g2} is a parasitic capacitance in the gap between the cache memory chip **311** and the chip **313**. The capacitance C_{b1} is a capacitance of the metal interconnect line **640***h* or **640***b* between the inter-chip buffer **704***a* or **701***a* and the metal pad **600***c* or **600***b* on the chip **313** or **311**. The capacitance C_{b2} is a capacitance of the metal pad **600***c* or **600***b* corresponding to the inter-chip buffer **704***a* or

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701*a* on the chip **313** or **311**. The capacitance C_{b3} is a parasitic capacitance correspondent to the inter-chip buffer **704***a* or **701***a* on the chip **313** or **311**.

[1117] Accordingly, the load or loading of the inter-chip buffer **702***a* or **703***a* shown in FIG. **39**A or **39**I can be defined. The load or loading of the inter-chip buffer **702***a* or **703***a*, such as the load or loading of the last stage inverter **425***b* or **426***b*, with drains of the NMOS transistor **752***a* or **753***a* and the PMOS transistor **752***b* or **753***b* connected to the metal pad **600***b* or **600***c*, of the two-stage cascade inter-chip driver shown in FIG. **39**C or **39**D, can be smaller than 2 pF, such as between 2 pF and 0.001 pF, exemplary smaller than 1 pF or smaller than 0.3 pF. For clock rate or signal frequency larger 1 G Hz, the load or loading or the size of the inter-chip buffer **702***a* or **703***a* shown in FIG. **39**A or **39**I can be smaller than 0.1 pF, such as between 0.1 pF and 0.001 pF.

[1118] The size of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* shown in FIG. **39**H or **39**J can be characterized by the load or loading of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a*. Referring to FIG. **39**H or **39**J, the load or loading of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* is total equivalent capacitance load of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a*, and the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* is designed with a certain size for driving the load or loading that equals a capacitance C_{a1} plus a capacitance C_{a2} plus a capacitance C_{a3} plus a capacitance C_{g1} plus a capacitance C_{g2} plus a capacitance C_{b1} plus a capacitance C_{b2} plus a capacitance C_{b3}. The capacitance C_{a1} is a capacitance of the metal interconnect line **640***b*, **640***d*, **640***f* or **640***h* between the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* and the metal pad **600***b* or **600***c* on the chip **311** or **313**. The capacitance C_{a2} is a capacitance of the metal pad **600***b* or **600***c* corresponding to the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* on the chip **311** or **313**. The capacitance C_{a3} is a parasitic capacitance correspondent to the inter-chip **701***a*, **702***a*, **703***a* or **704***a* on the chip **311** or **313**. The capacitance C_{g1} is a capacitance of the microbump **317**. The capacitance C_{g2} is a parasitic capacitance in the gap between the cache memory chip **311** and the chip **313**. The capacitance C_{b1} is a capacitance of the metal interconnect line **640***f*, **640***h*, **640***b* or **640***d* between the inter-chip buffer **703***a*, **704***a*, **701***a* or **702***a* and the metal pad **600***c* or **600***b* on the chip **313** or **311**. The capacitance C_{b2} is a capacitance of the metal pad **600***c* or **600***b* corresponding to the inter-chip buffer **703***a*, **704***a*, **701***a* or **702***a* on the chip **313** or **311**. The capacitance C_{b3} is a parasitic capacitance correspondent to the inter-chip buffer **703***a*, **704***a*, **701***a* or **702***a* on the chip **313** or **311**.

[1119] Accordingly, the load or loading of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* shown in FIG. **39**H or **39**J can be defined. The load or loading of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a*, such as the load or loading of a last stage tri-state driver, with drains of an NMOS transistor and a PMOS transistor connected to the metal pad **600***b* or **600***c*, of a multi-stage cascade tri-state buffer, can be smaller than 2 pF, such as between 2 pF and 0.001 pF, exemplary smaller than 1 pF or smaller than 0.3 pF. For clock rate or signal frequency larger **1**G Hz, the load or loading or the size of the inter-chip buffer **701***a*, **702***a*, **703***a* or **704***a* shown in FIG. **39**H or **39**J can be smaller than 0.1 pF, such as between 0.1 pF and 0.001 pF.

[1120] The size of the off-chip buffer **42***b* shown in FIG. **39**A or **39**H can be characterized by the load or loading of the off-chip buffer **42***b*. Referring to FIG. **39**A or **39**H, the load or loading of the off-chip buffer **42***b* is total equivalent capacitance load of the off-chip buffer **42***b*, and the off-chip buffer **42***b* is designed with a certain size for driving the load or loading that equals a capacitance C_{a1} plus a capacitance C_{a2} plus a capacitance C_{a3} plus a capacitance C_{a4} plus a capacitance C_{a5} plus a capacitance C_{xz}. The capacitance C_{a1} is a capacitance of the metal interconnect line **640***m* between the off-chip buffer **42***b* and the metal pad **600***s* on the cache memory chip **311** and between the off-chip buffer **42***b* and the metal pad **887** on the cache memory chip **311**. The capacitance C_a, is a capacitance of the metal pad **600***s* corresponding to the off-chip buffer **42***b* on the cache memory chip **311**. The capacitance C_{a3} is a capacitance of the metal pad **887** corresponding to the off-chip buffer **42***b* on the cache memory chip **311**. The capacitance C_{a4} is a parasitic capacitance correspondent to the off-chip buffer **42***b* on the cache memory chip **311**. The capacitance C_{a5} is a parasitic capacitance from the off-chip buffer **42***b* to the metal pad **600***s* and from the off-chip buffer **42***b* to the metal pad **887**. The capacitance C_{xz} can be a capacitance of a testing device and a parasitic capacitance in the testing device during wafer-level testing process, but after bonding with an external circuit, such as substrate **301** or **302**, the capacitance C_{xz} can include a capacitance of the metal bump or pillar **27**, plus a parasitic capacitance in the interconnection from the metal bump or pillar **27** to another chip or a passive device on the substrate **301** or **302**, plus a capacitance of metal interconnect lines in the substrate **301** or **302**, plus a capacitance of the another chip or the passive device on the substrate **301** or **302**, plus a parasitic capacitance correspondent to the another chip or the passive device on the substrate **301** or **302**.

[1121] Accordingly, the load or loading of the off-chip buffer **42***b* shown in FIG. **39**A or **39**H can be defined. The load or loading of the off-chip buffer **42***b*, such as the load or loading of a last stage driver, with drains of an NMOS transistor and a PMOS transistor connected to the metal pads **600***s* and **887**, of a multi-stage cascade inter-chip driver, can be larger than 2 pF, such as between 2 and 100 pF, exemplary larger than 5 pF or larger than 10 pF. The load or loading of the off-chip buffer **42***b* shown in FIG. **39**A or **39**H is larger than the load or loading of the inter-chip buffer **702***a* shown in FIG. **39**A or **39**H by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1122] The size of the off-chip buffer **42***b* shown in FIG. **39**I or **39**J can be characterized by the load or loading of the off-chip buffer **42***b*. Referring to FIG. **39**I or **39**J, the load or loading of the off-chip buffer **42***b* is total equivalent capacitance load of the off-chip buffer **42***b*, and the off-chip buffer **42***b* is designed with a certain size for driving the load or loading that equals a capacitance C_{a1} plus a capacitance C_{a2} plus a capacitance C_{a3} plus a capacitance C_{a4} plus a capacitance C_{xz}. The capacitance C_{a1} is a capacitance of the metal interconnect line **640***m* between the off-chip buffer **42***b* and the metal pad **600***s* on the cache memory chip **311**. The capacitance C_{a2} is a capacitance of the metal pad **600***s* corresponding to the off-chip buffer **42***b* on the cache memory chip **311**. The capacitance C_{a3} is a parasitic capacitance correspondent to the off-chip buffer **42***b* on the cache memory chip **311**. The capacitance C_{a4} is a parasitic capacitance from the off-chip buffer **42***b* to the metal pad **600***s*. The capacitance C_{xz} can be a capacitance of a testing device and a parasitic capacitance in the testing device during wafer-level testing process, but after bonding with an external circuit, such as substrate **301** or **302**, the capacitance C_{xz} can include a capacitance of the wirebonded wire **119***c*, plus a parasitic capacitance in the

interconnection from the wirebonded wire **119***c* to another chip or a passive device on the substrate **301** or **302**, plus a capacitance of metal interconnect lines in the substrate **301** or **302**, plus a capacitance of the another chip or the passive device on the substrate **301** or **302**, plus a parasitic capacitance correspondent to the another chip or the passive device on the substrate **301** or **302**.

[1123] Accordingly, the load or loading of the off-chip buffer **42***b* shown in FIG. **39**I or **39**J can be defined. The load or loading of the off-chip buffer **42***b,* such as the load or loading of a last stage driver, with drains of an NMOS transistor and a PMOS transistor connected to the metal pad **600***s,* of a multi-stage cascade inter-chip driver, can be larger than 2 pF, such as between 2 and 100 pF, exemplary larger than 5 pF or larger than 10 pF. The load or loading of the off-chip buffer **42***b* shown in FIG. **39**I or **39**J is larger than the load or loading of the inter-chip buffer **702***a* shown in FIG. **39**I or **39**J by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1124] The size of the off-chip buffer **42***c* shown in FIG. **39**A, **39**H, **39**I or **39**J can be characterized by the load or loading of the off-chip buffer **42***c*. Referring to FIG. **39**A, **39**H, **39**I or **39**J, the load or loading of the off-chip buffer **42***c* is total equivalent capacitance load of the off-chip buffer **42***c,* and the off-chip buffer **42***c* is designed with a certain size for driving the load or loading that equals a capacitance C_{a1} plus a capacitance C_{a2} plus a capacitance C_{a3} plus a capacitance C_{a4} plus a capacitance C_{xz}. The capacitance C_{a1} is a capacitance of the metal interconnect line **640***p* between the off-chip buffer **42***c* and the metal pad **600***w* on the chip **313**. The capacitance C_{a2} is a capacitance of the metal pad **600***w* corresponding to the off-chip buffer **42***c* on the chip **313**. The capacitance C_{a3} is a parasitic capacitance correspondent to the off-chip buffer **42***c* on the chip **313**. The capacitance C_{a4} is a parasitic capacitance from the off-chip buffer **42***c* to the metal pad **600***w.* The capacitance C_{xz} can be a capacitance of a testing device and a parasitic capacitance in the testing device during wafer-level testing process.

[1125] Accordingly, the load or loading of the off-chip buffer **42***c* shown in FIG. **39**A, **39**H, **39**I or **39**J can be defined. The load or loading of the off-chip buffer **42***c,* such as the load or loading of a last stage driver, with drains of an NMOS transistor and a PMOS transistor connected to the metal pad **600***w,* of a multi-stage cascade inter-chip driver, can be larger than 2 pF, such as between 2 and 100 pF, exemplary larger than 5 pF or larger than 10 pF. The load or loading of the off-chip buffer **42***c* shown in FIG. **39**A, **39**H, **39**I or **39**J is larger than the load or loading of the inter-chip buffer **703***a* shown in FIG. **39**A, **39**H, **39**I or **39**J by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1126] The size of the inter-chip buffer **702***a* or **703***a* shown in FIG. **39**A, **39**H, **39**I or **39**J can be characterized by a peak drive current of the inter-chip buffer **702***a* or **703***a,* and the size of the off-chip buffer **42***b* or **42***c* shown in FIG. **39**A, **39**H, **39**I or **39**J can be characterized by a peak drive current of the off-chip buffer **42***b* or **42***c*. The peak drive current of the off-chip buffer **42***b* or **42***c* is larger than the peak drive current of the inter-chip buffer **702***a* or **703***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1127] For example, regarding to the inter-chip buffer **702***a* shown in FIG. **39**A or **39**I, when the PMOS transistor **752***b* is on and the NMOS transistor **752***a* is off, the previously described load or loading driven by the inter-chip buffer **702***a* is charged with a charging current. When the NMOS transistor **752***a* is on and the PMOS transistor **752***b* is off, the load or loading the previously described load or loading driven by the inter-chip buffer **702***a* is discharged with a discharging current. The peak charging or discharging current (a function of bias-voltages) of the NMOS transistor **752***a* or PMOS transistor **752***b* can be used to define the peak drive current of the inter-chip buffer **702***a.* Regarding to the off-chip buffer **42***b* shown in FIG. **39**A or **39**I, when the PMOS transistor **4204** is on and the NMOS transistor **4203** is off, the previously described load or loading driven by the off-chip buffer **42***b* is charged with a charging current. When the NMOS transistor **4203** is on and the PMOS transistor **4204** is off, the previously described load or loading driven by the off-chip buffer **42***b* is discharged with a discharging current. The peak charging or discharging current (a function of bias-voltages) of the NMOS transistor **4203** or PMOS transistor **4204** can be used to define the peak drive current of the off-chip buffer **42***b.* The peak drive current of the off-chip buffer **42***b* is larger than the peak drive current of the inter-chip buffer **702***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1128] The size of the inter-chip buffer **702***a* or **703***a* shown in FIG. **39**A, **39**H, **39**I or **39**J can be characterized by an on-resistance of a transistor in the last stage driver of the inter-chip buffer **702***a* or **703***a,* and the size of the off-chip buffer **42***b* or **42***c* shown in FIG. **39**A, **39**H, **39**I or **39**J can be characterized by an on-resistance of a transistor in the last stage driver of the off-chip buffer **42***b* or **42***c.* The on-resistance of the off-chip buffer **42***b* or **42***c* is larger than the on-resistance of the inter-chip buffer **702***a* or **703***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1129] For example, regarding to the inter-chip buffer **702***a* shown in FIG. **39**A or **39**I, when the PMOS transistor **752***b* is on and the NMOS transistor **752***a* is off, the previously described load or loading driven by the inter-chip buffer **702***a* is charged, and the PMOS transistor **752***b* is equivalent to a resister with an on-resistance. When the NMOS transistor **752***a* is on and the PMOS transistor **752***b* is off, the previously described load or loading driven by the inter-chip buffer **702***a* is discharged, and the NMOS transistor **752***a* is equivalent to a resister with resistance of an on-resistance. The on-resistance (a function of bias-voltages) of the NMOS transistor **752***a* or PMOS transistor **752***b* can be used to characterize the size of the inter-chip buffer **702***a.* Regarding to the off-chip buffer **42***b* shown in FIG. **39**A or **39**I, when the PMOS transistor **4204** is on and the NMOS transistor **4203** is off, the previously described load or loading driven by the off-chip buffer **42***b* is charged, and the PMOS transistor **4204** is equivalent to a resister with an on-resistance. When the NMOS transistor **4203** is on and the PMOS transistor **4204** is off, the previously described load or loading driven by the off-chip buffer **42***b* is discharged, and the NMOS transistor **4203** is equivalent to a resister with an on-resistance. The on-resistance (a function of bias-voltages) of the NMOS transistor **4203** or PMOS transistor **4204** can be used to characterize the size of the off-chip buffer **42***b.*

[1130] The size of the inter-chip buffer **702***a* shown in FIG. **39**A or **39**I can be characterized by a ratio of a physical channel width to a physical channel length of the NMOS transistor **752***a* or PMOS transistor **752***b,* and the drains of the NMOS transistor **752***a* and the PMOS transistor **752***b* are connected to the metal pad **600***b* of the cache memory chip **311** through the metal interconnect line **640***d.* If the inter-chip

buffer **702***a* is the two-stage cascade inter-chip driver shown in FIG. **39**C, the size of the inter-chip buffer **702***a* can be characterized by the ratio of the physical channel width to the physical channel length of the NMOS transistor **752***a* or PMOS transistor **752***b* in the last stage driver **425***b,* and the drains of the NMOS transistor **752***a* and the PMOS transistor **752***b* are connected to the metal pad **600***b* of the cache memory chip **311** through the metal interconnect line **640***d.* The definition of the physical channel width and physical channel length of the NMOS transistor **752***a* or PMOS transistor **752***b* can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor **752***a* can be between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor **752***b* can be between 1 and 100, exemplary between 1 and 40.

[1131] The size of the inter-chip buffer **703***a* shown in FIG. **39**A or **39**I can be characterized by a ratio of a physical channel width to a physical channel length of the NMOS transistor **753***a* or PMOS transistor **753***b,* and the drains of the NMOS transistor **753***a* and the PMOS transistor **753***b* are connected to the metal pad **600***c* of the chip **313** through the metal interconnect line **640***f.* If the inter-chip buffer **703***a* is the two-stage cascade inter-chip driver shown in FIG. **39**D, the size of the inter-chip buffer **703***a* can be characterized by the ratio of the physical channel width to the physical channel length of the NMOS transistor **753***a* or PMOS transistor **753***b* in the last stage driver **426***b,* and the drains of the NMOS transistor **753***a* and the PMOS transistor **753***b* are connected to the metal pad **600***c* of the chip **313** through the metal interconnect line **640***f.* The definition of the physical channel width and physical channel length of the NMOS transistor **753***a* or PMOS transistor **753***b* can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor **753***a* is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor **753***b* is between 1 and 100, exemplary between 1 and 40.

[1132] The size of the off-chip buffer **42***b* shown in FIG. **39**A or **39**I can be characterized by a ratio of a physical channel width to a physical channel length of the NMOS transistor **4203** or PMOS transistor **4204**, and the drains of the NMOS transistor **4203** and the PMOS transistor **4204** are connected to the metal pad **600***s* or **887** of the cache memory chip **311** through the metal interconnect line **640***m.* If the off-chip buffer **42***b* is the two-stage cascade off-chip driver **421** shown in FIG. **11**A, the size of the off-chip buffer **42***b* can be characterized by the ratio of the physical channel width to the physical channel length of the NMOS transistor **4203** or PMOS transistor **4204** in the last stage driver **421**", and the drains of the NMOS transistor **4203** and the PMOS transistor **4204** are connected to the metal pad **600***s* or **887** of the cache memory chip **311** through the metal interconnect line **640***m.* The definition of the physical channel width and physical channel length of the NMOS transistor **4203** or PMOS transistor **4204** can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor **4203** can be larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300. The ratio of the physical channel width to the physical channel length of the PMOS transistor **4204** can be larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. The ratio of the physical channel width to the physical channel length of the NMOS transistor **4203** may be larger than the ratio of the physical channel width to the physical channel length of the NMOS transistor **752***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times. The ratio of the physical channel width to the physical channel length of the PMOS transistor **4204** may be larger than the ratio of the physical channel width to the physical channel length of the PMOS transistor **752***b* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1133] The size of the off-chip buffer **42***c* shown in FIG. **39**A or **39**I can be characterized by a ratio of a physical channel width to a physical channel length of the NMOS transistor **4203***a* or PMOS transistor **4204***a,* and the drains of the NMOS transistor **4203***a* and the PMOS transistor **4204***a* are connected to the metal pad **600***w* of the chip **313** through the metal interconnect line **640***p.* If the off-chip buffer **42***c* is the two-stage cascade off-chip driver shown in FIG. **39**F, the size of the off-chip buffer **42***c* can be characterized by the ratio of the physical channel width to the physical channel length of the NMOS transistor **4203***a* or PMOS transistor **4204***a* in the last stage driver **427***b,* and the drains of the NMOS transistor **4203***a* and the PMOS transistor **4204***a* are connected to the metal pad **600***w* of the chip **313** through the metal interconnect line **640***p.* The definition of the physical channel width and physical channel length of the NMOS transistor **4203***a* or PMOS transistor **4204***a* can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor **4203***a* is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300. The ratio of the physical channel width to the physical channel length of the PMOS transistor **4204***a* is larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. The ratio of the physical channel width to the physical channel length of the NMOS transistor **4203***a* may be larger than the ratio of the physical channel width to the physical channel length of the NMOS transistor **753***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and **100** times. The ratio of the physical channel width to the physical channel length of the PMOS transistor **4204***a* may be larger than the ratio of the physical channel width to the physical channel length of the PMOS transistor **753***b* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1134] The size of the inter-chip buffer **701***a* or **702***a* shown in FIG. **39**H or **39**J can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor of the tri-state driver of the inter-chip tri-state buffer, and the tri-state driver is connected to the metal pad **600***b* of the cache memory chip **311** through the metal interconnect line **640***b* or **640***d,* and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver is between 1 and 100, exemplary between 1 and 40. If the inter-chip buffer **701***a* or **702***a* is a multi-stage tri-state buffer, the size of the inter-chip buffer **701***a* or **702***a* can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor in the last stage tri-state

driver of the multi-stage tri-state buffer, and the last stage tri-state driver is connected to the metal pad **600***b* of the cache memory chip **311** through the metal interconnect line **640***b* or **640***d*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the last stage tri-state driver is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the last stage tri-state driver is between 1 and 100, exemplary between 1 and 40. The definition of the physical channel width and physical channel length of the NMOS transistor or PMOS transistor can be referred to as the illustration in FIGS. **21** and **22**.

[1135] The size of the inter-chip buffer **703***a* or **704***a* shown in FIG. **39**H or **39**J can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor of the tri-state driver of the inter-chip tri-state buffer, and the tri-state driver is connected to the metal pad **600***c* of the chip **313** through the metal interconnect line **640***f* or **640***h*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver is between 1 and 100, exemplary between 1 and 40. If the inter-chip buffer **703***a* or **704***a* is a multi-stage tri-state buffer, the size of the inter-chip buffer **703***a* or **704***a* can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor in the last stage tri-state driver of the multi-stage tri-state buffer, and the last stage tri-state driver is connected to the metal pad **600***c* of the chip **313** through the metal interconnect line **640***f* or **640***h*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the last stage tri-state driver is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the last stage tri-state driver is between 1 and 100, exemplary between 1 and 40. The definition of the physical channel width and physical channel length of the NMOS transistor or PMOS transistor can be referred to as the illustration in FIGS. **21** and **22**.

[1136] The size of the off-chip buffer **42***a* or **42***b* shown in FIG. **39**H or **39**J can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor of a tri-state driver of the off-chip tri-state buffer, and the tri-state driver is connected to the metal pad **600***t* or **600***s* of the cache memory chip **311** through the metal interconnect line **640***j* or **640***m*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver is larger than 60 such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. If the off-chip buffer **42***a* or **42***b* is a multi-stage tri-state buffer, the size of the off-chip buffer **42***a* or **42***b* can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor in the last stage tri-state driver of the multi-stage tri-state buffer, and the last stage tri-state driver is connected to the metal pad **600***t* or **600***s* of the cache memory chip **311** through the metal interconnect line **640***j* or **640***m*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the last stage tri-state driver is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the last stage tri-state driver is larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. The definition of the physical channel width and physical channel length of the NMOS transistor or PMOS transistor can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver of the off-chip tri-state buffer **42***a* or **42***b* shown in FIG. **39**H or **39**J may be larger than the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver of the inter-chip tri-state buffer **701***a* or **702***a* shown in FIG. **39**H or **39**J by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times. The ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver of the off-chip tri-state buffer **42***a* or **42***b* shown in FIG. **39**H or **39**J may be larger than the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver of the inter-chip tri-state buffer **701***a* or **702***a* shown in FIG. **39**H or **39**J by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1137] The size of the off-chip buffer **42***c* or **42***d* shown in FIG. **39**H or **39**J can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor of a tri-state driver of the off-chip tri-state buffer, and the tri-state driver is connected to the metal pad **600***w* or **600***x* of the chip **313** through the metal interconnect line **640***p* or **640***r*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver is larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. If the off-chip buffer **42***c* or **42***d* is a multi-stage tri-state buffer, the size of the off-chip buffer **42***c* or **42***d* can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor in the last stage tri-state driver of the multi-stage tri-state buffer, and the last stage tri-state driver is connected to the metal pad **600***w* or **600***x* of the chip **313** through the metal interconnect line **640***p* or **640***r*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the last stage tri-state driver is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the last stage tri-state driver is larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. The definition of the physical channel width and physical channel length of the NMOS transistor or PMOS transistor can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver of the off-chip tri-state buffer **42***c* or **42***d* shown in FIG. **39**H or **39**J may be larger than the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver of the inter-chip tri-

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state buffer **703***a* or **704***a* shown in FIG. **39**H or **39**J by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times. The ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver of the off-chip tri-state buffer **42***c* or **42***d* shown in FIG. **39**H or **39**J may be larger than the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver of the inter-chip tri-state buffer **703***a* or **704***a* shown in FIG. **39**H or **39**J by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1138] FIGS. **42**A-**42**O are cross-sectional views showing a process for forming the chip **313** shown in FIG. **37**A, **37**D, **38**A, **38**D, **39**A, **39**H, **39**I or **39**J. Referring to FIG. **42**A, a semiconductor wafer **10***a,* such as silicon wafer, is provided with a silicon substrate **1**, the previously described off-chip circuit **40***c* including the previously described off-chip buffer **42***c* and the previously described off-chip ESD circuit **43***c* in and/or over the silicon substrate **1**, the previously described off-chip circuit **40***d* including the previously described off-chip buffer **42***d* and the previously described off-chip ESD circuit **43***d* in and/or over the silicon substrate **1**, the previously described inter-chip circuits **20***e* and **20***f* in and/or over the silicon substrate **1**, the previously described internal circuits **20***g* and **20***h* in and/or over the silicon substrate **1**, multiple dielectric layers **30** over the silicon substrate **1**, multiple fine-line metal layers **60** over the silicon substrate **1**, multiple via plugs **60'** in vias **30'** of the dielectric layers **30**, and an insulating layer **5**, that is, passivation layer, over the fine-line metal layers **60**, over the dielectric layers **30**, over the off-chip circuits **40***c* and **40***d,* over the inter-chip circuits **20***e* and **20***f,* and over the internal circuits **20***g* and **20***h*.

[1139] The semiconductor wafer **10***a* has the previously described metal pads **600***c,* **600***w* and **600***x*. The metal pads **600***c,* **600***w* and **600***x* are provided by the topmost fine-line metal layer **60** under the passivation layer **5**, and include aluminum, aluminum-copper-alloy or electroplated copper. Each of the metal pads **600***c,* **600***w* and **600***x* may have a thickness between 0.5 and 3 micrometers or between 20 nanometers and 1.5 micrometers, and a width smaller than 1 micrometer, such as between 0.2 and 0.95 micrometers. Multiple openings **50** in the passivation layer **5** are over the metal pads **600***c,* **600***w* and **600***x* and expose them, and the metal pads **600***c,* **600***w* and **600***x* are at bottoms of the openings **50**. Each of the openings **50** may have a width between 10 and 100 micrometers, and preferably between 20 and 60 micrometers.

[1140] The silicon substrate **1** has a thickness t**1** between 600 and 1000 micrometers, between 50 micrometers and 1 millimeter or between 75 and 250 micrometers. Alternatively, the silicon substrate **1** can be replaced with other semiconductor substrate, such as silicon-germanium (SiGe) substrate or gallium arsenide (GaAs) substrate. The dielectric layers **30** are interposed respectively between the neighboring fine-line metal layers **60**, and the neighboring fine-line metal layers **60** are interconnected through the via plugs **60'** inside the dielectric layer **30**. The dielectric layers **30** can be formed by a suitable process or processes, e.g., by a CVD (Chemical Vapor Deposition) process, a PECVD (Plasma-Enhanced CVD) process, a High-Density-Plasma (HDP) CVD process or a spin-on coating method. The material of the dielectric layers **30** may include silicon oxide, silicon nitride, silicon oxynitride, silicon oxycarbide (SiOC) or silicon carbon nitride (SiCN). Each of the dielectric layers **30** can be composed of one or more inorganic layers, and may have a thickness between 0.1 and 1.5 micrometers. For example, each of the dielectric layers **30** may include a layer of silicon oxynitride or silicon carbon nitride and a layer of silicon oxide or silicon oxycarbide on the layer of silicon oxynitride or silicon carbon nitride. Alternatively, each of the dielectric layers **30** may include an oxide layer, such as silicon-oxide layer, having a thickness between 0.02 and 1.2 micrometers, and a nitride layer, such as silicon-nitride layer, having a thickness between 0.02 and 1.2 micrometers on the oxide layer.

[1141] Each of the fine-line metal layers **60** has a thickness between 20 nanometers and 1.5 micrometers, and preferably between 100 nanometers and 1 micrometer. Each of the fine-line metal layers **60** may include a metal trace having a width smaller than 1 micrometer, such as between 0.05 and 0.95 micrometers. The material of the fine-line metal layers **60** may include electroplated copper, aluminum, aluminum-copper alloy or a composite of the previously described materials.

[1142] For example, each of the fine-line metal layers **60** may include an electroplated copper layer having a thickness between 20 nanometers and 1.5 micrometers, and preferably between 100 nanometers and 1 micrometer, in one of the dielectric layers **30**, an adhesion/barrier layer, such as titanium-nitride layer, titanium-tungsten-alloy layer, tantalum-nitride layer, titanium layer or tantalum layer, at a bottom surface and sidewalls of the electroplated copper layer, and a seed layer of copper between the electroplated copper layer and the adhesion/barrier layer. The seed layer of copper is at the bottom surface and sidewalls of the electroplated copper layer and contacts with the bottom surface and sidewalls of the electroplated copper layer. The electroplated copper layer, the seed layer of copper and the adhesion/barrier layer can be formed by a suitable process or processes, e.g., by a damascene or double-damascene process including an electroplating process, a sputtering process and a chemical mechanical polishing (CMP) process.

[1143] Alternatively, each of the fine-line metal layers **60** may include an adhesion/barrier layer on a top surface of one of the dielectric layers **30**, a sputtered aluminum or aluminum-copper-alloy layer having a thickness between 20 nanometers and 1.5 micrometers, and preferably between 100 nanometers and 1 micrometer, on a top surface of the adhesion/barrier layer, and an anti-reflection layer on a top surface of the sputtered aluminum or aluminum-copper-alloy layer. The sputtered aluminum or aluminum-copper-alloy layer, the adhesion/barrier layer and the anti-reflection layer can be formed by a suitable process or processes, e.g., by a process including a sputtering process and an etching process. Sidewalls of the sputtered aluminum or aluminum-copper-alloy layer are not covered by the adhesion/barrier layer and the anti-reflection layer. The adhesion/barrier layer and the anti-reflection layer can be a titanium layer, a titanium-nitride layer or a titanium-tungsten layer.

[1144] The semiconductor wafer **10***a* has the previously described metal interconnect lines **640***e,* **640***f,* **640***g,* **640***h,* **640***n,* **640***p,* **640***q* and **640***r* each including a portion provided by the fine-line metal layers **60** and the via plugs **60'**, but the metal interconnect lines **640***e* and **640***g* are not shown in FIGS. **42**A-**42**O. The semiconductor wafer **10***a* also includes the previously described testing interface circuits **333***c* and **333***d* (not shown in FIGS. **42**A-**42**O). The metal interconnect line **640***e* can connect the inter-chip circuit **20***e* and the internal circuit **20***g,* and the metal interconnect line **640***g* can connect the inter-chip circuit **20***f* and the internal circuit **20***h*. The inter-chip circuit **20***e* can be connected to one of the metal

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pads **600***c* and to the testing interface circuit **333***c* through the metal interconnect line **640***f*. The inter-chip circuit **20***f* can be connected to another one of the metal pads **600***c* and to the testing interface circuit **333***d* through the metal interconnect line **640***h*. The metal interconnect line **640***n* can connect the off-chip buffer **42***c* and the testing interface circuit **333***c*, and the metal interconnect line **640***q* can connect the off-chip buffer **42***d* and the testing interface circuit **333***d*. The off-chip buffer **42***c* can be connected to the off-chip ESD circuit **43***c* and to the testing metal pad **600***w* through the metal interconnect line **640***p*. The off-chip buffer **42***d* can be connected to the off-chip ESD circuit **43***d* and to the testing metal pad **600***x* through the metal interconnect line **640***r*.

[1145] The passivation layer **5** can protect the inter-chip circuits **20***e* and **20***f*, the internal circuits **20***g* and **20***h*, the off-chip circuits **40***c* and **40***d* and the fine-line metal layers **60** from being damaged by moisture and foreign ion contamination. In other words, mobile ions (such as sodium ion), transition metals (such as gold, silver and copper) and impurities can be prevented from penetrating through the passivation layer **5** to the inter-chip circuits **20***e* and **20***f*, the internal circuits **20***g* and **20***h*, the off-chip circuits **40***c* and **40***d* and the fine-line metal layers **60**.

[1146] The passivation layer **5** can be formed by a suitable process or processes, e.g., by a chemical vapor deposition (CVD) method, and typically has a thickness larger than 0.2 micrometers, such as between 0.3 and 1.5 micrometers. The passivation layer **5** is commonly made of silicon oxide (such as SiO_2), silicon nitride (such as Si_3N_4), silicon oxynitride (such as SiON), silicon oxycarbide (SiOC), PSG (phosphosilicate glass), silicon carbon nitride (such as SiCN) or a composite of the previously described materials.

[1147] The passivation layer **5** can be composed of one or more inorganic layers. For example, the passivation layer **5** can be a composite layer of an oxide layer, such as silicon oxide or silicon oxycarbide (SiOC), having a thickness between 0.2 and 1.2 micrometers and a nitride layer, such as silicon nitride, silicon oxynitride or silicon carbon nitride (SiCN), having a thickness between 0.2 and 1.2 micrometers on the oxide layer. Alternatively, the passivation layer **5** can be a single layer of silicon nitride, silicon oxynitride or silicon carbon nitride (SiCN) having a thickness between 0.2 and 1.2 micrometers. In a exemplary case, the passivation layer **5** includes a topmost inorganic layer of the semiconductor wafer **10***a*, and the topmost inorganic layer of the semiconductor wafer **10***a* can be a silicon nitride layer having a thickness larger than 0.2 micrometers, such as between 0.2 and 1.5 micrometers.

[1148] Referring to FIG. **42**B, after providing the semiconductor wafer **10***a* shown in FIG. **42**A, a flux or insulating material **33** can be formed in the openings **50** and on the metal pads **600***c*, **600***w* and **600***x* exposed by the openings **50**. Next, referring to FIG. **42**C, with the step being illustrated with a reverse figure for simple explanation, the silicon substrate **1** of the semiconductor wafer **10***a* is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) a backside **1***a* of the silicon substrate **1**.

[1149] Next, referring to FIG. **42**D, with the steps being illustrated with a reverse figure for simple explanation, multiple through-silicon vias **11** (only two of them are shown in FIGS. **42**D-**42**N) are formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing regions **60***a* of the fine-line metal layers **60**, and an insulating layer **3** is formed on the backside **1***a* of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11**. The through-silicon vias **11** penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. Each of the through-silicon vias **11** may have a diameter or width W**1** between 5 and 100 micrometers or between 3 and 50 micrometers, and a depth between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers. The insulating layer **3**, for example, may include a nitride layer, such as silicon-nitride layer, a polymer layer, such as polyimide layer, benzocyclobutene layer or polybenzoxazole layer, a silicon-oxynitride layer, a silicon-carbon-nitride (SiCN) layer, a silicon-oxycarbide (SiOC) layer or a silicon-oxide layer. The process of forming the through-silicon vias **11** and the insulating layer **3** as shown in FIG. **42**D can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and the insulating layer **3** as illustrated in FIGS. **24**D-**24**H or FIGS. **241**-**24**N. The specification of the insulating layer **3** shown in FIG. **42**D can be referred to as the specification of the insulating layer **3** as illustrated in FIGS. **24**D-**24**H or FIGS. **24**I-**24**N.

[1150] Next, referring to FIG. **42**E, with the step being illustrated with a reverse figure for simple explanation, an interconnecting structure **88** provided by two metal layers **4** and **9** can be formed in the through-silicon vias **11**, on the insulating layer **3**, on the regions **60***a* of the fine-line metal layers **60** and at the backside **1***a* of the thinned silicon substrate **1**, and the metal layer **4** is composed of an adhesion/barrier layer **4***a* on the insulating layer **3**, in the through-silicon vias **11** and on the regions **60***a* of the fine-line metal layers **60** exposed by the through-silicon vias **11**, and a seed layer **4***b* on the adhesion/barrier layer **4***a*. Sidewalls of the metal layer **9** are not covered by the metal layer **4**. The process of forming the interconnecting structure **88** as shown in FIG. **42**E can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The specification of the metal layer **4** including the adhesion/barrier layer **4***a* and the seed layer **4***b* as shown in FIG. **42**E can be referred to as the specification of the metal layer **4** including the adhesion/barrier layer **4***a* and the seed layer **4***b* as illustrated in FIG. **25**A. The specification of the metal layer **9** shown in FIG. **42**E can be referred to as the specification of the metal layer **9** as illustrated in FIG. **25**D.

[1151] Next, referring to FIG. **42**F, with the step being illustrated with a reverse figure for simple explanation, a polymer layer **14** is formed on the metal layer **9**, on the insulating layer **3** and at sidewalls of the interconnecting structure **88** using a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process. Two openings **14***a* in the polymer layer **14** are over two regions of the metal layer **9** and expose them. The polymer layer **14** has a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers, larger than that of each of the dielectric layers **30**, and larger than that of the passivation layer **5**. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[1152] Next, referring to FIG. **42**G, with the steps being illustrated with a reverse figure for simple explanation, an adhesion/barrier layer **16***z* having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and

preferably between 1.5 and 100 nanometers, can be formed on the polymer layer **14** and on the regions of the metal layer **9** exposed by the openings **14***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **18***z* having a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, can be formed on the adhesion/barrier layer **16***z* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **16***z* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **18***z* may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[1153] For example, when the adhesion/barrier layer **16***z* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **14** and on the regions of the metal layer **9** exposed by the openings **14***a*, the seed layer **18***z* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the titanium-containing layer.

[1154] Alternatively, when the adhesion/barrier layer **16***z* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **14** and on the regions of the metal layer **9** exposed by the openings **14***a*, the seed layer **18***z* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the tantalum-containing layer.

[1155] After forming the seed layer **18***z*, a photoresist layer **31**, such as positive-type photoresist layer or negtive-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 60 micrometers, is formed on the seed layer **18***z* by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **31** is patterned with the processes of exposure and development to form multiple openings **31***a* in the photoresist layer **31** exposing the seed layer **18***z*. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **31** during the process of exposure.

[1156] Next, a metal layer **27***y* is formed on the seed layer **18***z* of any previously described material exposed by the openings **31***a* and in the openings **31***a* by using an electroplating process, and then a solder layer **27***z* is formed on the metal layer **27***y* in the openings **31***a* by using an electroplating process. Each of the metal layer **27***y* and the solder layer **27***z* has a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, larger than that of the seed layer **18***z*, and larger than that of the adhesion/barrier layer **16***z*. The material of the metal layer **27***y* includes copper and/or nickel, and the material of the solder layer **27***z* includes bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The solder layer **27***z* can be used to be bonded with the cache memory chip **321**.

[1157] For example, the metal layer **27***y* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of copper with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **18***z*, preferably the previously described copper layer **18***z*, exposed by the openings **31***a*, and the solder layer **27***z* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of copper by using an electroplating process.

[1158] Alternatively, the metal layer **27***y* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of nickel with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **18***z*, preferably the previously described copper or nickel layer **18***z*, exposed by the openings **31***a*, and the solder layer **27***z* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of nickel by using an electroplating process.

[1159] Alternatively, the metal layer **27***y* can be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **18***z*, preferably the previously described copper layer **18***z*, exposed by the openings **31***a*, and then electroplating a nickel layer with a thickness larger than 0.2 micrometers, such as between 0.3 and 6 micrometers, and preferably between 1 and 3 micrometers, on the electroplated copper layer. The solder layer **27***z* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the electroplated nickel layer of the metal layer **27***y* by using an electroplating process.

[1160] Next, referring to FIG. **42**H, with the steps being illustrated with a reverse figure for simple explanation, the photoresist layer **31** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **31** could remain on the seed layer **18***z* not under the metal layer **27***y*. Thereafter, the residuals can be removed from the seed layer **18***z* with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. Next, the seed layer **18***z* not under the metal layer **27***y* is removed, and then the adhesion/barrier layer **16***z* not under the metal layer **27***y* is removed.

[1161] For example, the seed layer **18***z* not under the metal layer **27***y* and the adhesion/barrier layer **16***z* not under the metal layer **27***y* can be removed by a dry etching process, such

as Ar sputtering etching process, reactive ion etching (RIE) process or ion milling process.

[1162] Alternatively, the seed layer **18***z* not under the metal layer **27***y* and the adhesion/barrier layer **16***z* not under the metal layer **27***y* can be removed by a wet etching process. When the seed layer **18***z* is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4. When the adhesion/barrier layer **16***z* is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide. When the adhesion/barrier layer **16***z* is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide.

[1163] In case the seed layer **18***z* not under the metal layer **27***y* is removed using a wet etching process, an undercut is formed under the metal layer **27***y* overhanging the seed layer **18***z*. The seed layer **18***z* under the metal layer **27***y* has a first sidewall recessed from a second sidewall of the metal layer **27***y*, and a distance between the first sidewall and the second sidewall is between 0.1 and 2 micrometers.

[1164] Accordingly, as shown in FIG. **42**H, a bottom scheme **103** at the backside I a of the thinned silicon substrate **1** is formed with the insulating layer **3**, the polymer layer **14**, the interconnecting structure **88** provided by the metal layers **4** and **9**, and multiple microbumps **317***c*, that is, metal bumps, provided by the adhesion/barrier layer **16***z*, the seed layer **18***z*, the metal layer **27***y* and the solder layer **27***z*. Each of the microbumps **317***c* has a height larger than 2 micrometers, such as between 2 and 70 micrometers, and preferably between 5 and 50 micrometers, and a width or diameter larger than 3 micrometers, such as between 3 and 30 micrometers. A pitch P**2** between neighboring two microbumps **317***c* can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. One of the microbumps **317***c* can be connected to another one of the microbumps **317***c* through the interconnecting structure **88**. The microbumps **317***c* are used to be bonded with the cache memory chip **321**. The inter-chip circuit **20***e* can be connected to the interconnecting structure **88** through the metal interconnect line **640***f*, to the microbumps **317***c* through the metal interconnect line **640***f* and the interconnecting structure **88**, and to the inter-chip circuit **20***f* through the metal interconnect line **640***f*, the interconnecting structure **88** and the metal interconnect line **640***h*. The inter-chip circuit **20***f* can be connected to the interconnecting structure **88** through the metal interconnect line **640***h*, and to the microbumps **317***c* through the metal interconnect line **640***h* and the interconnecting structure **88**.

[1165] Alternatively, the interconnecting structure **88** can be used for a power interconnect, such as power plane, power bus, power trace or power line, to connect with a power node of the inter-chip circuit **20***e*, a power node of the internal circuit **20***g*, a power node of the off-chip buffer **42***c*, a node of the off-chip ESD circuit **43***c*, a power node of the testing interface circuit **333***c*, a power node of the inter-chip circuit **20***f*, a power node of the internal circuit **20***h*, a power node of the off-chip buffer **42***d*, a node of the off-chip ESD circuit **43***d*, and a power node of the testing interface circuit **333***d* through the through-silicon vias **11**. The power nodes of the inter-chip circuit **20***e*, the internal circuit **20***g*, the off-chip buffer **42***c* and the testing interface circuit **333***c* can be connected to the power nodes of the inter-chip circuit **20***f*, the internal circuit **20***h*, the off-chip buffer **42***d* and the testing interface circuit **333***d* through the interconnecting structure **88**. The node of the off-chip ESD circuit **43***c* can be connected to the node of the off-chip ESD circuit **43***d* through the interconnecting structure **88**.

[1166] Alternatively, the interconnecting structure **88** can be used for a ground interconnect, such as ground plane, ground bus, ground trace or ground line, to connect with a ground node of the inter-chip circuit **20***e*, a ground node of the internal circuit **20***g*, a ground node of the off-chip buffer **42***c*, a node of the off-chip ESD circuit **43***c*, a ground node of the testing interface circuit **333***c*, a ground node of the inter-chip circuit **20***f*, a ground node of the internal circuit **20***h*, a ground node of the off-chip buffer **42***d*, a node of the off-chip ESD circuit **43***d*, and a ground node of the testing interface circuit **333***d* through the through-silicon vias **11**. The ground nodes of the inter-chip circuit **20***e*, the internal circuit **20***g*, the off-chip buffer **42***c* and the testing interface circuit **333***c* can be connected to the ground nodes of the inter-chip circuit **20***f*, the internal circuit **20***h*, the off-chip buffer **42***d* and the testing interface circuit **333***d* through the interconnecting structure **88**. The node of the off-chip ESD circuit **43***c* can be connected to the node of the off-chip ESD circuit **43***d* through the interconnecting structure **88**.

[1167] Referring to FIG. **421**, after forming the microbumps **317***c* shown in FIG. **42**H, the flux or insulating material **33** can be removed to expose the metal pads **600***c*, **600***w* and **600***x* exposed by the openings **50** in the passivation layer **5**. Next, referring to FIG. **42**J, a polymer layer **95** can be optionally formed on the passivation layer **5** of the semiconductor wafer **10***a*. Multiple openings **950** in the polymer layer **95** are over the metal pads **600***c*, **600***w* and **600***x* exposed by the openings **50** and expose them. The polymer layer **95** may have a thickness larger than 2 micrometers, such as between 3 and 50 micrometers, and preferably between 2 and 30 micrometers, larger than that of the passivation layer **5**, and larger than that of each of the dielectric layers **30**. The material of the polymer layer **95** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[1168] Next, referring to FIG. **42**K, an adhesion/barrier layer **32***y* having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, can be formed on the polymer layer **95** and on the metal pads **600***c*, **600***w* and **600***x* exposed by the openings **950** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **32***z* having a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, can be formed on the adhesion/barrier layer **32***y* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **32***y* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **32***z* may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[1169] When the adhesion/barrier layer **32***y* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the poly-

mer layer **95** and on the metal pads **600***c*, **600***w* and **600***x* exposed by the openings **950**, the seed layer **32***z* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the titanium-containing layer.

[1170] Alternatively, when the adhesion/barrier layer **32***y* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **95** and on the metal pads **600***c*, **600***w* and **600***x* exposed by the openings **950**, the seed layer **32***z* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the tantalum-containing layer.

[1171] After forming the seed layer **32***z*, a photoresist layer **71**, such as positive-type photoresist layer or negtive-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 60 micrometers, is formed on the seed layer **32***z* by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **71** is patterned with the processes of exposure and development to form multiple openings **710** in the photoresist layer **71** exposing the seed layer **32***z*, and the openings **710** are over the metal pads **600***c*, but over the metal pads **600***w* and **600***x* for testing is no opening in the photoresist layer **71**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **71** during the process of exposure.

[1172] Next, a metal layer **34***y* is formed on the seed layer **32***z* of any previously described material exposed by the openings **710** and in the openings **710** by using an electroplating process, and then a solder layer **34***z* is formed on the metal layer **34***y* in the openings **710** by using an electroplating process. Both of the metal layer **34***y* and the solder layer **34***z* have a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, larger than that of the seed layer **32***z* and larger than that of the adhesion/barrier layer **32***y*. The material of the metal layer **34***y* includes copper and/or nickel, and the material of the solder layer **34***z* includes bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The solder layer **34***z* can be used to be bonded with the cache memory chip **311**.

[1173] For example, the metal layer **34***y* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of copper with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***z*, preferably the previously described copper layer **32***z*, exposed by the openings **710**, and the solder layer **34***z* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of copper by using an electroplating process.

[1174] Alternatively, the metal layer **34***y* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of nickel with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***z*, preferably the previously described copper or nickel layer **32***z*, exposed by the openings **710**, and the solder layer **34***z* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of nickel by using an electroplating process.

[1175] Alternatively, the metal layer **34***y* can be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***z*, preferably the previously described copper layer **32***z*, exposed by the openings **710**, and then electroplating a nickel layer with a thickness larger than 0.2 micrometers, such as between 0.3 and 6 micrometers, and preferably between 1 and 3 micrometers, on the electroplated copper layer. The solder layer **34***z* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the electroplated nickel layer of the metal layer **34***y* by using an electroplating process.

[1176] Next, referring to FIG. **42**L, the photoresist layer **71** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **71** could remain on the seed layer **32***z* not under the metal layer **34***y*. Thereafter, the residuals can be removed from the seed layer **32***z* with a plasma, such as an O_2 plasma or a plasma containing fluorine of below **200**PPM and oxygen. Next, the seed layer **32***z* not under the metal layer **34***y* is removed, and then the adhesion/barrier layer **32***y* not under the metal layer **34***y* is removed.

[1177] For example, the seed layer **32***z* not under the metal layer **34***y* and the adhesion/barrier layer **32***y* not under the metal layer **34***y* can be removed by a dry etching process, such as Ar sputtering etching process, reactive ion etching (RIE) process or ion milling process.

[1178] Alternatively, the seed layer **32***z* not under the metal layer **34***y* and the adhesion/barrier layer **32***y* not under the metal layer **34***y* can be removed by a wet etching process. When the seed layer **32***z* is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4. When the adhesion/barrier layer **32***y* is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide. When the adhesion/barrier layer **32***y* is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide.

[1179] In case the seed layer **32***z* not under the metal layer **34***y* is removed using a wet etching process, an undercut is formed under the metal layer **34***y* overhanging the seed layer **32***z*. The seed layer **32***z* under the metal layer **34***y* has a first sidewall recessed from a second sidewall of the metal layer

34*y*, and a distance between the first sidewall and the second sidewall is between 0.1 and 2 micrometers.

[1180] Accordingly, as shown in FIG. **42**L, multiple microbumps **317***d*, that is, metal bumps, provided by the adhesion/barrier layer **32***y*, the seed layer **32***z*, the metal layer **34***y* and the solder layer **34***z* are formed on the metal pads **600***c* exposed by the openings **50** and **950**, on the polymer layer **95**, and at the active side of the thinned silicon substrate **1**, and are used to be bonded with the cache memory chip **311**. Each of the microbumps **317***d* has a height larger than 2 micrometers, such as between 2 and 70 micrometers, and preferably between 5 and 50 micrometers, and a width or diameter larger than 3 micrometers, such as between 3 and 30 micrometers. A pitch P**3** between neighboring two microbumps **317***d* can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. The metal interconnect lines **640***f* and **640***h* connect with the microbumps **317***d* through the openings **50** and **950**. The inter-chip circuit **20***e* can be connected to one of the microbumps **317***d* through the metal interconnect line **640***f*, and the inter-chip circuit **20***f* can be connected to another one of the microbumps **317***d* through the metal interconnect line **640***h*. There are no microbumps formed on the metal pads **600***w* and **600***x* exposed by the openings **50** and **950**, that is, the metal pads **600***w* and **600***x* are exposed by the openings **50** and **950** for testing.

[1181] Alternatively, referring to FIG. **42**M, the polymer layer **95** can be omitted, that is, the adhesion/barrier layer **32***y* can be formed on the passivation layer **5** and on the metal pads **600***c* exposed by the openings **50** in the passivation layer **5**. Accordingly, the microbumps **317***d* provided by the adhesion/barrier layer **32***y*, the seed layer **32***z*, the metal layer **34***y* and the solder layer **34***z* can be formed on the metal pads **600***c* exposed by the openings **50**, on the passivation layer.**5**, and at the active side of the thinned silicon substrate **1**.

[1182] Referring to FIG. **42**N, after forming the microbumps **317***d*, the semiconductor wafer **10***a* can be cut into a plurality of the chip **313** shown in FIG. **37**A, **37**D, **38**A, **38**D, **39**A, **39**H, **39**I or **39**J by a die-sawing process. Alternatively, referring to FIG. **42**O, the steps shown in FIGS. **42**B-**42**I can be omitted, that is, after providing the semiconductor wafer **10***a* shown in FIG. **42**A, the steps shown in FIGS. **42**J-**42**L can be performed to form the polymer layer **95** and the microbumps **317***d*, and then the semiconductor wafer **10***a* can be cut into a plurality of the chip **313** shown in FIG. **37**B, **37**C, **38**B, **38**C, **39**A, **39**H, **39**I or **39**J by a die-sawing process.

[1183] An IC structure **6***c* of the chip **313** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D contains the inter-chip circuits **20***e* and **20***f*, the internal circuits **20***g* and **20***h*, the off-chip circuit **40***c* including the off-chip buffer **42***c* and the off-chip ESD circuit **43***c*, the off-chip circuit **40***d* including the off-chip buffer **42***d* and the off-chip ESD circuit **43***d*, the dielectric layers **30**, the vias **30'**, the fine-line metal layers **60**, the via plugs **60'**, the testing interface circuits **333***c* and **333***d*, and the metal interconnect lines **640***e*, **640***f*, **640***g*, **640***h*, **640***n*, **640***p*, **640***q* and **640***r* as illustrated in FIG. **42**N or **42**O.

[1184] FIGS. **43**A-**43**E are cross-sectional views showing a process for forming a semiconductor wafer finalized to be cut into a plurality of the cache memory chip **321** shown in FIG. **37**A, **37**D, **38**A or **38**D. Referring to FIG. **43**A, a semiconductor wafer **10***b*, such as silicon wafer, is provided with a silicon substrate **1**, multiple inter-chip circuits **20***j* and **20***k* in and/or over the silicon substrate **1**, multiple internal circuits **20***m* and **20***n* in and/or over the silicon substrate **1**, an off-chip circuit **40***e* including an off-chip buffer **42***e* and an off-chip ESD circuit **43***e* in and/or over the silicon substrate **1**, an off-chip circuit **40***f* including an off-chip buffer **42***f* and an off-chip ESD circuit **43***f* in and/or over the silicon substrate **1**, multiple dielectric layers **30** over the silicon substrate **1**, multiple fine-line metal layers **60** over the silicon substrate **1**, multiple via plugs **60'** in vias **30'** of the dielectric layers **30**, and an insulating layer **5**, that is, passivation layer, over the fine-line metal layers **60**, over the dielectric layers **30**, over the inter-chip circuits **20***j* and **20***k*, over the off-chip circuits **40***e* and **40***f*, and over the internal circuits **20***m* and **20***n*.

[1185] The semiconductor wafer **10***b* has the previously described metal pads **600***d*, **600***y* and **600***z*. The metal pads **600***d*, **600***y* and **600***z* are provided by the topmost fine-line metal layer **60** under the passivation layer **5**, and include aluminum, aluminum-copper-alloy or electroplated copper. Each of the metal pads **600***d*, **600***y* and **600***z* may have a thickness between 0.5 and 3 micrometers or between 20 nanometers and 1.5 micrometers, and a width smaller than 1 micrometer, such as between 0.2 and 0.95. micrometers. Multiple openings **50** in the passivation layer **5** are over the metal pads **600***d*, **600***y* and **600***z* and expose them, and the metal pads **600***d*, **600***y* and **600***z* are at bottoms of the openings **50**. Each of the openings **50** may have a width between 10 and 100 micrometers, and preferably between 20 and 60 micrometers.

[1186] The semiconductor wafer **10***b* has multiple metal interconnect lines **640***s*, **640***t*, **640***u*, **640***v*, **640***w*, **640***x*, **640***y* and **640***z* each including a portion provided by the fine-line metal layers **60** and the via plugs **60'**. The off-chip buffer **42***e* can be connected to the off-chip ESD circuit **43***e* and to the testing metal pad **600***z* through the metal interconnect line **640***s*. The off-chip buffer **42***f* can be connected to the off-chip ESD circuit **43***f* and to the testing metal pad **600***y* through the metal interconnect line **640***t*. The internal circuit **20***m* can be connected to the inter-chip circuit **20***j* through the metal interconnect line **640***y*, and the internal circuit **20***n* can be connected to the inter-chip circuit **20***k* through the metal interconnect line **640***z*.

[1187] The semiconductor wafer **10***b* also includes two testing interface circuits **333***e* and **333***f* (not shown). The testing interface circuit **333***e* can be connected to the off-chip buffer **42***e* through the metal interconnect line **640***u*, and the testing interface circuit **333***f* can be connected to the off-chip buffer **42***f* through the metal interconnect line **640***v*. The inter-chip circuit **20***j* can be connected to the testing interface circuit **333***e* and to one of the metal pads **600***d* through the metal interconnect line **640***w*. The inter-chip circuit **20***k* can be connected to the testing interface circuit **333***f* and to another one of the metal pads **600***d* through the metal interconnect line **640***x*.

[1188] The passivation layer **5** can protect the inter-chip circuits **20***j* and **20***k*, the internal circuits **20***m* and **20***n*, the off-chip circuits **40***e* and **40***f*, the testing interface circuits **333***e* and **333***f* and the fine-line metal layers **60** from being damaged by moisture and foreign ion contamination. In other words, mobile ions (such as sodium ion), transition metals (such as gold, silver and copper) and impurities can be prevented from penetrating through the passivation layer **5** to the inter-chip circuits **20***j* and **20***k*, the internal circuits **20***m* and **20***n*, the off-chip circuits **40***e* and **40***f*, the testing interface circuits **333***e* and **333***f* and the fine-line metal layers **60**. The

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specification of the silicon substrate **1**, the dielectric layers **30**, the fine-line metal layers **60** and the passivation layer **5** as shown in FIG. **43**A can be referred to as the specification of the silicon substrate **1**, the dielectric layers **30**, the fine-line metal layers **60** and the passivation layer **5** as illustrated in FIG. **42**A, respectively.

[1189] Next, referring to FIG. **43**B, a polymer layer **95** can be optionally formed on the passivation layer **5** of the semiconductor wafer **10***b*. Multiple openings **950** in the polymer layer **95** are over the metal pads **600***d*, **600***y* and **600***z* exposed by the openings **50** and expose them. The specification of the polymer layer **95** as shown in FIG. **43**B can be referred to as the specification of the polymer layer **95** as illustrated in FIG. **42**J.

[1190] Next, referring to FIG. **43**C, an adhesion/barrier layer **32***w* having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, can be formed on the polymer layer **95** and on the metal pads **600***d*, **600***y* and **600***z* exposed by the openings **950** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **32***x* having a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, can be formed on the adhesion/barrier layer **32***w* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **32***w* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **32***x* may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[1191] When the adhesion/barrier layer **32***w* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **95** and on the metal pads **600***d*, **600***y* and **600***z* exposed by the openings **950**, the seed layer **32***x* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the titanium-containing layer.

[1192] Alternatively, when the adhesion/barrier layer **32***w* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **95** and on the metal pads **600***d*, **600***y* and **600***z* exposed by the openings **950**, the seed layer **32***x* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the tantalum-containing layer.

[1193] After forming the seed layer **32***x*, a photoresist layer **71**, such as positive-type photoresist layer or negtive-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 60 micrometers, is formed on the seed layer **32***x* by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **71** is patterned with the processes of exposure and development to form multiple openings **710** in the photoresist layer **71** exposing the seed layer **32***x*, and the openings **710** are over the metal pads **600***d*, but over the metal pads **600***y* and **600***z* for testing is no opening in the photoresist layer **71**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **71** during the process of exposure.

[1194] Next, a metal layer **34***w* is formed on the seed layer **32***x* of any previously described material exposed by the openings **710** and in the openings **710** by using an electroplating process, and then a solder layer **34***x* is formed in the openings **710** and on the metal layer **34***w* in the openings **710** by using an electroplating process. Both of the metal layer **34***w* and the solder layer **34***x* have a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, larger than that of the seed layer **32***x* and larger than that of the adhesion/barrier layer **32***w*. The material of the metal layer **34***w* includes copper and/or nickel, and the material of the solder layer **34***x* includes bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The solder layer **34***x* can be used to be bonded with the chip **313**.

[1195] For example, the metal layer **34***w* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of copper with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***x*, preferably the previously described copper layer **32***x*, exposed by the openings **710**, and the solder layer **34***x* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of copper by using an electroplating process.

[1196] Alternatively, the metal layer **34***w* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of nickel with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***x*, preferably the previously described copper or nickel layer **32***x*, exposed by the openings **710**, and the solder layer **34***x* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of nickel by using an electroplating process.

[1197] Alternatively, the metal layer **34***w* can be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***x*, preferably the previously described copper layer **32***x*, exposed by the openings **710**, and then electroplating a nickel layer with a thickness larger than 0.2 micrometers, such as between 0.3 and 6 micrometers, and preferably between 1 and 3 micrometers, on the electroplated copper layer. The solder layer **34***x* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-

copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the electroplated nickel layer of the metal layer **34***w* by using an electroplating process.

[1198] Next, referring to FIG. **43**D, the photoresist layer **71** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **71** could remain on the seed layer **32***x* not under the metal layer **34***w*. Thereafter, the residuals can be removed from the seed layer **32***x* with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. Next, the seed layer **32***x* not under the metal layer **34***w* is removed, and then the adhesion/barrier layer **32***w* not under the metal layer **34***w* is removed.

[1199] For example, the seed layer **32***x* not under the metal layer **34***w* and the adhesion/barrier layer **32***w* not under the metal layer **34***w* can be removed by a dry etching process, such as Ar sputtering etching process, reactive ion etching (RIE) process or ion milling process.

[1200] Alternatively, the seed layer **32***x* not under the metal layer **34***w* and the adhesion/barrier layer **32***w* not under the metal layer **34***w* can be removed by a wet etching process. When the seed layer **32***x* is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4. When the adhesion/barrier layer **32***w* is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide. When the adhesion/barrier layer **32***w* is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide.

[1201] In case the seed layer **32***x* not under the metal layer **34***w* is removed using a wet etching process, an undercut is formed under the metal layer **34***w* overhanging the seed layer **32***x*. The seed layer **32***x* under the metal layer **34***w* has a first sidewall recessed from a second sidewall of the metal layer **34***w*, and a distance between the first sidewall and the second sidewall is between 0.1 and 2 micrometers.

[1202] Accordingly, as shown in FIG. **43**D, multiple microbumps **317***e*, that is, metal bumps, provided by the adhesion/barrier layer **32***w*, the seed layer **32***x*, the metal layer **34***w* and the solder layer **34***x* are formed on the metal pads **600***d* exposed by the openings **50** and **950**, on the polymer layer **95**, and at the active side of the thinned silicon substrate **1**. Each of the microbumps **317***e* has a height larger than 2 micrometers, such as between 2 and 70 micrometers, and preferably between 5 and 50 micrometers, and a width or diameter larger than 3 micrometers, such as between 3 and 30 micrometers. A pitch P2 between neighboring two microbumps **317***e* can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. There are no microbumps formed on the metal pads **600***y* and **600***z* exposed by the openings **50** and **950**, that is, the metal pads **600***y* and **600***z* are exposed by the openings **50** and **950** for testing.

[1203] The inter-chip circuit **20***j* and the testing interface circuit **333***e* can be connected to one of the microbumps **317***e* through the metal interconnect line **640***w* and through one of the openings **50**, and the inter-chip circuit **20***k* and the testing interface circuit **333***f* can be connected to another one of the microbumps **317***e* through the metal interconnect line **640***x* and through another one of the openings **50**. In a case, one of the microbumps **317***e* can be connected to signal nodes of the inter-chip circuit **20***j* and the testing interface circuit **333***e* through the metal interconnect line **640***w*, and another one of the microbumps **317***e* can be connected to signal nodes of the inter-chip circuit **20***k* and the testing interface circuit **333***d* through the metal interconnect line **640***x*. In another case, one of the microbumps **317***e* can be connected to power or ground nodes of the inter-chip circuit **20***j* and the testing interface circuit **333***e* through the metal interconnect line **640***w*, and another one of the microbumps **317***e* can be connected to power or ground nodes of the inter-chip circuit **20***k* and the testing interface circuit **333***d* through the metal interconnect line **640***x*.

[1204] Alternatively, referring to FIG. **43**E, the polymer layer **95** can be omitted, that is, the adhesion/barrier layer **32***w* can be formed on the passivation layer **5** and on the metal pads **600***d* exposed by the openings **50** in the passivation layer **5**. Accordingly, the microbumps **317***e* provided by the adhesion/barrier layer **32***w*, the seed layer **32***x*, the metal layer **34***w* and the solder layer **34***x* can be formed on the metal pads **600***d* exposed by the openings **50**, on the passivation layer **5**, and at the active side of the thinned silicon substrate **1**.

[1205] The semiconductor wafer **10***b* shown in FIG. **43**D or **43**E can be finalized to be cut into a plurality of the cache memory chip **321**.

[1206] FIGS. **44**A-**44**C are cross-sectional views showing a process for bonding the chip **313** with the semiconductor wafer **10***b* finalized to be cut into a plurality of the cache memory chip **321** as shown in FIG. **37**A, **37**D, **38**A or **38**D.

[1207] Referring to FIG. **44**A, the chip **313** shown in FIG. **42**N can be bonded with the semiconductor wafer **10***b* shown in FIG. **43**D by joining the solder layer **27***z* of the microbumps **317***c* with the solder layer **34***x* of the microbumps **317***e* using a reflow or heating process. During the reflow or heating process, the solder layer **27***z* and the solder layer **34***x* are melted into a solder layer **35** including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, between the metal layers **27***y* and **34***w*. Accordingly, the previously described microbumps **317***a* provided by the adhesion/barrier layers **16***z* and **32***w*, the seed layers **18***z* and **32***x*, the metal layers **27***y* and **34***w* and the solder layer **35** can be formed between the metal pads **600***d* of the semiconductor wafer **10***b* and multiple contact points of the interconnecting structure **88** of the bottom scheme **103** of the chip **313**. Each of the microbumps **317***a* has a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers, and contacts with one of the metal pads **600***d* and with one of the contact points of the interconnecting structure **88**. The pitch between neighboring two microbumps **317***a* can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. The metal pads **600***d* can be connected to the interconnecting structure **88** through the microbumps **317***a*.

[1208] Next, referring to FIG. **44**B, the previously described underfill **107***e* without fillers, such as a polymer, is filled into a gap between the chip **313** and the cache memory chip **321**, and encloses the microbumps **317***a*. Next, referring to FIG. **44**C, the semiconductor wafer **10***b* can be cut to singularize a plurality of stacked unit including the chips **313** and **321** connected to each other through the microbumps

317*a*. An IC structure **6***d* of the cache memory chip **321** shown in FIG. **37**A, **37**D, **38**A or **38**D contains the inter-chip circuits **20***j* and **20***k*, the internal circuits **20***m* and **20***n*, the off-chip circuit **40***e* including the off-chip buffer **42***e* and the off-chip ESD circuit **43***e*, the off-chip circuit **40***f* including the off-chip buffer **42***f* and the off-chip ESD circuit **43***f*, the test interface circuits **333***e* and **333***f*, the dielectric layers **30**, the vias **30'**, the fine-line metal layers **60**, the via plugs **60'**, and the metal interconnect lines **640***s*, **640***t*, **640***u*, **640***v*, **640***w*, **640***x*, **640***y* and **640***z*.

[1209] FIG. **45**A is an example of a circuit diagram showing interface circuits of the chip **313** and the cache memory chip **321** shown in FIG. **37**A, **37**D, **38**A, **38**D or **44**C. For detailed description about the circuit diagram of the chip **313** shown in FIG. **45**A, please refer to the illustration in FIGS. **39**A, **39**D-**39**J and **40**A-**40**F. FIG. **45**B is another example of the circuit diagram showing interface circuits of the chip **313** and the cache memory chip **321** shown in FIG. **37**A, **37**D, **38**A, **38**D or **44**C. The circuit diagram shown in FIG. **45**B is similar to that shown in FIG. **45**A except that the inter-chip buffers **701***a*, **702***a*, **703***a* and **704***a* are designed with inter-chip tri-state buffers each including a tri-state driver and a tri-state receiver, and the off-chip buffers **42***c*, **42***d*, **42***e* and **42***f* are designed with off-chip tri-state buffers each including a tri-state driver and a tri-state receiver. For detailed description about the circuit diagram of the chip **313** shown in FIG. **45**B, please refer to the illustration in FIGS. **39**H and **40**A-**40**F.

[1210] Referring to FIGS. **45**A and **45**B, the cache memory chip **321** shown in FIG. **45**A or **45**B includes the inter-chip circuits **20***j* and **20***k*, the internal circuits **20***m* and **20***n*, the off-chip circuit **40***e* including the off-chip buffer **42***e* and the off-chip ESD circuit **43***e*, the off-chip circuit **40***f* including the off-chip buffer **42***f* and the off-chip ESD circuit **43***f*, and the testing interface circuits **333***e* and **333***f*.

[1211] The inter-chip circuit **20***j* includes an inter-chip buffer **701***a* and an inter-chip ESD circuit **701***b*. The inter-chip buffer **701***a* of the inter-chip circuit **20***j* has a first node FN**1** and a second node SN**1**, and the inter-chip ESD circuit **701***b* has a node En connected to the first node FN**1**. The first node FN**1** of the inter-chip buffer **701***a* can be connected to the node En of the inter-chip ESD circuit, **701***b*, to a first terminal F**5** of the testing interface circuit **333***e* through the metal interconnect line **640***w* of the cache memory chip **321**, to the left one of the metal pads **600***d*, including aluminum or electroplated copper, of the cache memory chip **321** through the metal interconnect line **640***w*, to the left one of the microbumps **317***a* through the metal interconnect line **640***w* and the left one of the metal pads **600***d*, and to the second node SN**3** of the inter-chip buffer **703***a* of the chip **313** through the metal interconnect line **640***w*, the left one of the metal pads **600***d*, the left one of the microbumps **317***a* and the metal interconnect line **640***f* of the chip **313**. The second node SN**1** of the inter-chip buffer **701***a* can be connected to the internal circuit **20***m* through the metal interconnect line **640***y* of the cache memory chip **321**. The specification of the inter-chip buffer **701***a* as shown in FIG. **45**A or **45**B can be referred to as the specification of the inter-chip buffer **701***a* as illustrated in FIG. **39**A, **39**B or **39**H, and the specification of the inter-chip ESD circuit **701***b* as shown in FIG. **45**A or **45**B can be referred to as the specification of the inter-chip ESD circuit **701***b* as illustrated in FIG. **39**A or **39**H.

[1212] The inter-chip circuit **20***k* includes an inter-chip buffer **702***a* and an inter-chip ESD circuit **702***b*. The inter-chip buffer **702***a* of the inter-chip circuit **20***k* has a first node FN**2** and a second node SN**2**, and the inter-chip ESD circuit **702***b* has a node En connected to the second node SN**2**. The first node FN**2** of the inter-chip buffer **702***a* can be connected to the internal circuit **20***n* through the metal interconnect line **640***z* of the cache memory chip **321**. The second node SN**2** of the inter-chip buffer **702***a* can be connected to the node En of the inter-chip ESD circuit **702***b*, to a first terminal F**6** of the testing interface circuit **333***f* through the metal interconnect line **640***x* of the cache memory chip **321**, to the right one of the metal pads **600***d*, including aluminum or electroplated copper, of the cache memory chip **321** through the metal interconnect line **640***x*, to the right one of the microbumps **317***a* through the metal interconnect line **640***x* and the right one of the metal pads **600***d*, and to the first node FN**4** of the inter-chip buffer **704***a* of the chip **313** through the metal interconnect line **640***x*, the right one of the metal pads **600***d*, the right one of the microbumps **317***a* and the metal interconnect line **640***h* of the chip **313**. The specification of the inter-chip buffer **702***a* as shown in FIG. **45**A or **45**B can be referred to as the specification of the inter-chip buffer **702***a* as illustrated in FIG. **39**A, **39**C or **39**H, and the specification of the inter-chip ESD circuit **702***b* as shown in FIG. **45**A or **45**B can be referred to as the specification of the inter-chip ESD circuit **702***b* as illustrated in FIGS. **39**A or **39**H.

[1213] The inter-chip ESD circuits **701***b* and **702***b* are used for the inter-chip buffers **20***j* and **20***k* between the chip **313** and the cache memory chip **321** for electrostatic charge protection during the chip packaging or assembly manufacturing process. Alternatively, no ESD circuit can be required for the inter-chip buffers **20***j* and **20***k* between the chip **313** and the cache memory chip **321**, that is, the inter-chip ESD circuits **701***b* and **702***b* can be omitted. In other words, there is no ESD circuit connected to the metal interconnect lines **640***w* and **640***x*.

[1214] The off-chip buffer **42***e* has a first node FN**5** and a second node SN**5**, and the off-chip ESD circuit **43***e* has a node En connected to the first node FN**5** and to the testing metal pad **600***z*. The first node FN**5** of the off-chip buffer **42***e* can be connected to the node En of the off-chip ESD circuit **43***e*, and to the testing metal pad **600***z*, including aluminum or electroplated copper, of the cache memory chip **321** through the metal interconnect line **640***s*. The second node SN**5** of the off-chip buffer **42***e* can be connected to a second terminal S**5** of the testing interface circuit **333***e* through the metal interconnect line **640***u* of the cache memory chip **321**. The specification of the off-chip buffer **42***e* as shown in FIG. **45**A or **45**B can be referred to as the specification of the off-chip buffer **42***a* as illustrated in FIG. **39**A or **39**H, and the specification of the off-chip ESD circuit **43***e* as shown in FIG. **45**A or **45**B can be referred to as the specification of the off-chip ESD circuit **43***a* as illustrated in FIG. **39**A or **39**H.

[1215] The off-chip buffer **42***f* has a first node FN**6** and a second node SN**6**, and the off-chip ESD circuit **43***f* has a node En connected to the second node SN**6** and to the testing metal pad **600***y*. The first node FN**6** of the off-chip buffer **42***f* can be connected to a second terminal S**6** of the testing interface circuit **333***f* through the metal interconnect line **640***v* of the cache memory chip **321**. The second node SN**6** of the off-chip buffer **42***f* can be connected to the node En of the off-chip ESD circuit **43***f*, and to the testing metal pad **600***y*, including aluminum or electroplated copper, of the cache memory chip **321** through the metal interconnect line **640***t*. The specification of the off-chip buffer **42***f* as shown in FIG. **45**A or **45**B

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can be referred to as the specification of the off-chip buffer **42***a* as illustrated in FIG. **39**A or **39**H, and the specification of the off-chip ESD circuit **43***e* as shown in FIG. **45**A or **45**B can be referred to as the specification of the off-chip ESD circuit **43***a* as illustrated in FIG. **39**A or **39**H.

[1216] Each of the internal circuits **20***m* and **20***n* shown in FIG. **45**A or **45**B can be a NOR gate, a NAND gate, an AND gate, an OR gate, a flash memory cell, a dynamic-random-access-memory (DRAM) cell, a static-random-access-memory (SRAM) cell, a non-volatile memory cell, an erasable programmable read-only memory (EPROM) cell, a read-only memory (ROM) cell, a magnetic random access memory (MRAM) cell, an analog-to-digital (A/D) converter, a digital-to-analog (D/A) converter, an operational amplifier, a sense amplifier, an inverter, an adder, a multiplexer, a diplexer, a multiplier, a complementary-metal-oxide-semiconductor (CMOS) device, a bi-polar CMOS device, a bipolar circuit or an analog circuit. Each of the internal circuits **20***m* and **20***n* shown in FIG. **45**A or **45**B may include a NMOS transistor having a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.1 and 20, ranging from, e.g., about 0.1 and 10 or ranging from, e.g., about 0.2 and 2. Alternatively, each of the internal circuits **20***m* and **20***n* shown in FIG. **45**A or **45**B may include a PMOS transistor having a ratio of a physical channel width thereof to a physical channel length thereof ranging from, e.g., about 0.2 and 40, ranging from, e.g., about 0.2 and 40 or ranging from, e.g., about 0.4 and 4.

[1217] Both of the test interface circuits **333***e* and **333***f* shown in FIG. **45**A or **45**B can be a scan test circuit, and the scan test circuit can be performed at the wafer level testing before the cache memory chip **321** is sawed or diced apart from a wafer or at the package level testing after the chips **321** and **313** are joined with each other, and the scan test circuit is used to test flip flops by input the scan-in signal or output the scan-out signal.

[1218] The size of the inter-chip buffer **702***a* shown in FIG. **45**A can be characterized by a ratio of a physical channel width to a physical channel length of the NMOS transistor **752***a* or PMOS transistor **752***b*, and the drains of the NMOS transistor **752***a* and the PMOS transistor **752***b* are connected to the metal pad **600***d* of the cache memory chip **321** through the metal interconnect line **640***x*. If the inter-chip buffer **702***a* is the two-stage cascade inter-chip driver shown in FIG. **39**C, the size of the inter-chip buffer **702***a* can be characterized by the ratio of the physical channel width to the physical channel length of the NMOS transistor **752***a* or PMOS transistor **752***b* in the last stage driver **425***b*, and the drains of the NMOS transistor **752***a* and the PMOS transistor **752***b* are connected to the metal pad **600***d* of the cache memory chip **321** through the metal interconnect line **640***x*. The definition of the physical channel width and physical channel length of the NMOS transistor **752***a* or PMOS transistor **752***b* can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor **752***a* can be between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor **752***b* can be between 1 and 100, exemplary between 1 and 40.

[1219] The size of the off-chip buffer **42***f* shown in FIG. **45**A can be characterized by a ratio of a physical channel width to a physical channel length of the NMOS transistor **4203** or PMOS transistor **4204**, and the drains of the NMOS transistor **4203** and the PMOS transistor **4204** are connected to the testing metal pad **600***y* of the cache memory chip **321** through the metal interconnect line **640***t*. If the off-chip buffer **42***f* is the two-stage cascade off-chip driver **421** shown in FIG. **11**A, the size of the off-chip buffer **42***f* can be characterized by the ratio of the physical channel width to the physical channel length of the NMOS transistor **4203** or PMOS transistor **4204** in the last stage driver **421"**, and the drains of the NMOS transistor **4203** and the PMOS transistor **4204** are connected to the testing metal pad **600***y* of the cache memory chip **321** through the metal interconnect line **640***t*. The definition of the physical channel width and physical channel length of the NMOS transistor **4203** or PMOS transistor **4204** can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor **4203** can be larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300. The ratio of the physical channel width to the physical channel length of the PMOS transistor **4204** can be larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. The ratio of the physical channel width to the physical channel length of the NMOS transistor **4203** of the off-chip buffer **42***f* may be larger than the ratio of the physical channel width to the physical channel length of the NMOS transistor **752***a* of the inter-chip buffer **702***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times. The ratio of the physical channel width to the physical channel length of the PMOS transistor **4204** of the off-chip buffer **42***f* may be larger than the ratio of the physical channel width to the physical channel length of the PMOS transistor **752***b* of the inter-chip buffer **702***a* by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1220] The size of the inter-chip buffer **701***a* or **702***a* shown in FIG. **45**B can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor of the tri-state driver of the inter-chip tri-state buffer, and the tri-state driver is connected to one of the metal pad **600***d* of the cache memory chip **321** through the metal interconnect line **640***w* or **640***x*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver is between 1 and 100, exemplary between 1 and 40. If the inter-chip buffer **701***a* or **702***a* is a multi-stage tri-state buffer, the size of the inter-chip buffer **701***a* or **702***a* can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor in the last stage tri-state driver of the multi-stage tri-state buffer, and the last stage tri-state driver is connected to one of the metal pad **600***d* of the cache memory chip **321** through the metal interconnect line **640***w* or **640***x*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the last stage tri-state driver is between 1 and 50, exemplary between 1 and 20, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the last stage tri-state driver is between 1 and 100, exemplary between 1 and 40. The definition of the physical channel width and physical channel length of the NMOS transistor or PMOS transistor can be referred to as the illustration in FIGS. **21** and **22**.

[1221] The size of the off-chip buffer **42***e* or **42***f* shown in FIG. **45**B can be characterized by a ratio of a physical channel

width to a physical channel length of an NMOS transistor or PMOS transistor of a tri-state driver of the off-chip tri-state buffer, and the tri-state driver is connected to the metal pad **600***z* or **600***y* of the cache memory chip **321** through the metal interconnect line **640***s* or **640***t*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver is larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. If the off-chip buffer **42***e* or **42***f* is a multi-stage tri-state buffer, the size of the off-chip buffer **42***e* or **42***f* can be characterized by a ratio of a physical channel width to a physical channel length of an NMOS transistor or PMOS transistor in the last stage tri-state driver of the multi-stage tri-state buffer, and the last stage tri-state driver is connected to the metal pad **600***z* or **600***y* of the cache memory chip **321** through the metal interconnect line **640***s* or **640***t*, and the ratio of the physical channel width to the physical channel length of the NMOS transistor of the last stage tri-state driver is larger than 30, such as between 30 and 20000, exemplary larger than 50, such as between 50 and 300, and the ratio of the physical channel width to the physical channel length of the PMOS transistor of the last stage tri-state driver is larger than 60, such as between 60 and 40000, exemplary larger than 100, such as between 100 and 600. The definition of the physical channel width and physical channel length of the NMOS transistor or PMOS transistor can be referred to as the illustration in FIGS. **21** and **22**. The ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver of the off-chip tri-state buffer **42***e* or **42***f* shown in FIG. **45**B may be larger than the ratio of the physical channel width to the physical channel length of the NMOS transistor of the tri-state driver of the inter-chip tri-state buffer **701***a* or **702***a* shown in FIG. **45**B by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times. The ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver of the off-chip tri-state buffer **42***e* or **42***f* shown in FIG. **45**B may be larger than the ratio of the physical channel width to the physical channel length of the PMOS transistor of the tri-state driver of the inter-chip tri-state buffer **701***a* or **702***a* shown in FIG. **45**B by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 100 times.

[1222] Each of the inter-chip ESD circuits **701***b* and **702***b* and each of the off-chip ESD circuits **43***e* and **43***f* may include one or more ESD (electro static discharge) units each composed of two reverse-biased diodes or of a PMOS transistor and an NMOS transistor.

[1223] The size of the inter-chip ESD circuit **701***b* or **702***b* of the cache memory chip **321** can be defined as a loading or capacitance of the inter-chip ESD circuit **701***b* or **702***b*, and the size of the off-chip ESD circuit **43***e* or **43***f* of the cache memory chip **321** can be defined as a loading or capacitance of the off-chip ESD circuit **43***e* or **43***f*. In a case, each of the inter-chip ESD circuits **701***b* and **702***b* of the cache memory chip **321** has a loading or capacitance smaller than 2 pF (pico Farads), such as between 0.01 and 2 pF, exemplary smaller than 0.5 pF, such as between 0.01 and 0.5 pF, and each of the large off-chip ESD circuits **43***e* and **43***f* of the cache memory chip **321** has a loading or capacitance larger than 2 pF, such as between 2 and 100 pF, exemplary larger than 5 pF, such as between 5 and 100 pF. In another case, each of the inter-chip ESD circuits **701***b* and **702***b* of the cache memory chip **321** has a loading or capacitance smaller than 1 pF, such as between 0.01 and 1 pF, and each of the large off-chip ESD circuits **43***e* and **43***f* of the cache memory chip **321** has a loading or capacitance larger than 1 pF, such as between 1 and 100 pF.

[1224] Alternatively, the size of the inter-chip ESD circuit **701***b* or **702***b* of the cache memory chip **321** can be defined as an active area of the inter-chip ESD circuit **701***b* or **702***b*, and the size of the large off-chip ESD circuit **43***e* or **43***f* of the cache memory chip **321** can be defined as an active area of the large off-chip ESD circuit **43***e* or **43***f*. Calculating or defining the active area of each of the inter-chip ESD circuits **701***b* and **702***b* and the active area of each of the off-chip ESD circuits **43***e* and **43***f* can be referred to as the step illustrated in FIGS. **40**A-**40***f*.

[1225] For example, each of the inter-chip ESD circuits **701***b* and **702***b* of the cache memory chip **321** may have an active area smaller than 1300 square millimeters, such as between 6.5 and 1300 square millimeters, exemplary smaller than 325 square millimeters, such as between 6.5 and 325 square millimeters, and each of the off-chip ESD circuits **43***e* and **43***f* of the cache memory chip **321** may have an active area larger than 1300 square millimeters, such as between 1300 and 65000 square millimeters, exemplary larger than 3250 square millimeters, such as between 3250 and 65000 square millimeters. Alternatively, each of the inter-chip ESD circuits **701***b* and **702***b* of the cache memory chip **321** may have an active area smaller than 650 square millimeters, and each of the off-chip ESD circuits **43***e* and **43***f* of the cache memory chip **321** may have an active area larger than 650 square millimeters.

[1226] The size of the off-chip ESD circuit **43***e* of the cache memory chip **321**, defined as the active area of the off-chip ESD circuit **43***e* or the loading or capacitance of the off-chip ESD circuit **43***e*, can be larger than the size of the inter-chip ESD circuit **701***b* of the cache memory chip **321**, defined as the active area of the inter-chip ESD circuit **701***b* or the loading or capacitance of the inter-chip ESD circuit **701***b*, by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 50 times.

[1227] The size of the off-chip ESD circuit **43***f* of the cache memory chip **321**, defined as the active area of the off-chip ESD circuit **43***f* or the loading or capacitance of the off-chip ESD circuit **43***f*, can be larger than the size of the inter-chip ESD circuit **702***b* of the cache memory chip **321**, defined as the active area of the inter-chip. ESD circuit **702***b* or the loading or capacitance of the inter-chip ESD circuit **702***b*, by more than 3 times, 10 times, 25 times or 50 times, such as between 3 and 50 times.

[1228] FIGS. **46**A-**46**M are cross-sectional views showing a process for forming a semiconductor wafer finalized to be cut into a plurality of the cache memory chip **311** shown in FIG. **37**A, **37**B, **38**A or **38**B. Referring to FIG. **46**A, a semiconductor wafer **10***c*, such as silicon wafer, is provided with a silicon substrate **1**, the previously described off-chip circuit **40***a* including the off-chip buffer **42***a* and the off-chip ESD circuit **43***a* in and/or over the silicon substrate **1**, the off-chip circuit **40***b* including the off-chip buffer **42***b* and the off-chip ESD circuit **43***b* in and/or over the silicon substrate **1**, the inter-chip circuits **20***a* and **20***b* in and/or over the silicon substrate **1**, the internal circuits **20***c* and **20***d* in and/or over the silicon substrate **1**, multiple dielectric layers **30** over the sili-

con substrate **1**, multiple fine-line metal layers **60** over the silicon substrate **1**, multiple via plugs **60'** in vias **30'** of the dielectric layers **30**, and an insulating layer **5**, that is, passivation layer, over the fine-line metal layers **60**, over the dielectric layers **30**, over the off-chip circuits **40***a* and **40***b*, over the inter-chip circuits **20***a* and **20***b*, and over the internal circuits **20***c* and **20***d*.

[1229] The semiconductor wafer **10***c* has the previously described metal pads **600***b*, **600***s* and **600***t*. The metal pads **600***b*, **600***s* and **600***t* are provided by the topmost fine-line metal layer **60** under the passivation layer **5**, and include aluminum, aluminum-copper-alloy or electroplated copper. Each of the metal pads **600***b*, **600***s* and **600***t* may have a thickness between 0.5 and 3 micrometers or between 20 nanometers and 1.5 micrometers, and a width smaller than 1 micrometer, such as between 0.2 and 0.95 micrometers. Multiple openings **50** in the passivation layer **5** are over the metal pads **600***b*, **600***s* and **600***t* and expose them, and the metal pads **600***b*, **600***s* and **600***t* are at bottoms of the openings **50**. Each of the openings **50** may have a width between 10 and 100 micrometers, and preferably between 20 and 60 micrometers.

[1230] The semiconductor wafer **10***c* has the previously described metal interconnect lines **640***a*, **640***b*, **640***c*, **640***d*, **640***i*, **640***j*, **640***k* and **640***m* each including a portion provided by the fine-line metal layers **60** and the via plugs **60'**. The semiconductor wafer **10***c* also includes the previously described testing interface circuits **333***a* and **333***b* (not shown in FIGS. **46**A-**46**N). The internal circuit **20***c* can be connected to the inter-chip circuit **20***a* through the metal interconnect line **640***a*, and the internal circuit **20***d* can be connected to the inter-chip circuit **20***b* through the metal interconnect line **640***c*. The inter-chip circuit **20***a* can be connected to one of the metal pads **600***b* and to the testing interface circuit **333***a* through the metal interconnect line **640***b*. The inter-chip circuit **20***b* can be connected to another one of the metal pads **600***b* and to the testing interface circuit **333***b* through the metal interconnect line **640***d*. The testing interface circuit **333***a* can be connected to the off-chip buffer **42***a* through the metal interconnect line **640***i*, and the testing interface circuit **333***b* can be connected to the off-chip buffer **42***b* through the metal interconnect line **640***k*. The off-chip buffer **42***a* can be connected to the off-chip ESD circuit **43***a* and to the testing metal pad **600***t* through the metal interconnect line **640***j*. The off-chip buffer **42***b* can be connected to the off-chip ESD circuit **43***b* and to the testing metal pad **600***s* through the metal interconnect line **640***m*.

[1231] The passivation layer **5** can protect the inter-chip circuits **20***a* and **20***b*, the internal circuits **20***c* and **20***d*, the off-chip circuits **40***a* and **40***b*, the testing interface circuits **333***a* and **333***b* and the fine-line metal layers **60** from being damaged by moisture and foreign ion contamination. In other words, mobile ions (such as sodium ion), transition metals (such as gold, silver and copper) and impurities can be prevented from penetrating through the passivation layer **5** to the inter-chip circuits **20***a* and **20***b*, the internal circuits **20***c* and **20***d*, the off-chip circuits **40***a* and **40***b*, the testing interface circuits **333***a* and **333***b* and the fine-line metal layers **60**. The specification of the silicon substrate **1**, the dielectric layers **30**, the fine-line metal layers **60** and the passivation layer **5** as shown in FIG. **46**A can be referred to as the specification of the silicon substrate I, the dielectric layers **30**, the fine-line metal layers **60** and the passivation layer **5** as illustrated in FIG. **42**A, respectively.

[1232] Referring to FIG. **46**B, after providing the semiconductor wafer **10***c* shown in FIG. **46**A, a flux or insulating material **33** can be formed in the openings **50** and on the metal pads **600***b*, **600***s* and **600***t* exposed by the openings **50**. Next, referring to FIG. **46**C, with the step being illustrated with a reverse figure for simple explanation, the silicon substrate **1** of the semiconductor wafer **10***c* is thinned to a thickness t**2** between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers by mechanically grinding or chemically mechanically polishing (CMP) a backside **1***a* of the silicon substrate **1**.

[1233] Next, referring to FIG. **46**D, with the steps being illustrated with a reverse figure for simple explanation, multiple through-silicon vias **11** (only two of them are shown in FIGS. **46**A-**46**N) are formed in the thinned silicon substrate **1** and in at least one dielectric layer **30**, exposing regions **60***a* of the fine-line metal layers **60**, and an insulating layer **3** is formed on the backside I a of the thinned silicon substrate **1** and on sidewalls of the through-silicon vias **11**. The through-silicon vias **11** penetrate completely through the thinned silicon substrate **1** and the dielectric layer(s) **30**. Each of the through-silicon vias **11** may have a diameter or width W**1** between 5 and 100 micrometers or between 3 and 50 micrometers, and a depth between 1 and 10 micrometers, between 3 and 50 micrometers or between 10 and 150 micrometers. The insulating layer **3**, for example, may include a nitride layer, such as silicon-nitride layer, a polymer layer, such as polyimide layer, benzocyclobutene layer or polybenzoxazole layer, a silicon-oxynitride layer, a silicon-carbon-nitride (SiCN) layer, a silicon-oxycarbide (SiOC) layer or a silicon-oxide layer. The process of forming the through-silicon vias **11** and the insulating layer **3** as shown in FIG. **46**D can be referred to as the process of forming the through-silicon vias **11***a*, **11***b*, **11***c*, **11***d* and **11***e* and the insulating layer **3** as illustrated in FIGS. **24**D-**24**H or FIGS. **241**-**24**N. The specification of the insulating layer **3** shown in FIG. **46**D can be referred to as the specification of the insulating layer **3** as illustrated in FIGS. **24**D-**24**H or FIGS. **24**I-**24**N.

[1234] Next, referring to FIG. **46**E, with the step being illustrated with a reverse figure for simple explanation, multiple interconnecting structures **88** provided by two metal layers **4** and **9** can be formed in the through-silicon vias **11**, on the insulating layer **3**, on the regions **60***a* of the fine-line metal layers **60** and at the backside **1***a* of the thinned silicon substrate **1**, and the metal layer **4** is composed of an adhesion/barrier layer **4***a* on the insulating layer **3**, in the through-silicon vias **11** and on the regions **60***a* of the fine-line metal layers **60** exposed by the through-silicon vias **11**, and a seed layer **4***b* on the adhesion/barrier layer **4***a*. Sidewalls of the metal layer **9** are not covered by the metal layer **4**. The process of forming the interconnecting structures **88** as shown in FIG. **46**E can be referred to as the process of forming the interconnecting structures **88** as illustrated in FIGS. **25**A-**25**F. The specification of the metal layer **4** including the adhesion/barrier layer **4***a* and the seed layer **4***b* as shown in FIG. **46**E can be referred to as the specification of the metal layer **4** including the adhesion/barrier layer **4***a* and the seed layer **4***b* as illustrated in FIG. **25**A. The specification of the metal layer **9** shown in FIG. **46**E can be referred to as the specification of the metal layer **9** as illustrated in FIG. **25**D.

[1235] The left one of the interconnecting structures **88** can be connected to the off-chip buffer **42***a*, to the off-chip ESD circuit **43***a*, and to the testing metal pad **600***t* through one or

more of the through-silicon vias **11** and through the metal interconnect line **640***j*. The right one of the interconnecting structures **88** can be connected to the off-chip buffer **42***b*, to the off-chip ESD circuit **43***b*, and to the testing metal pad **600***s* through one or more of the through-silicon vias **11** and through the metal interconnect line **640***m*.

[1236] The middle one of the interconnecting structures **88** can be used for a power interconnect, such as power plane, power bus, power trace or power line, to connect with a power node of the inter-chip circuit **20***a*, a power node of the internal circuit **20***c*, a power node of the off-chip buffer **42***a*, a node of the off-chip ESD circuit **43***a*, a power node of the testing interface circuit **333***a*, a power node of the inter-chip circuit **20***b*, a power node of the internal circuit **20***d*, a power node of the off-chip buffer **42***b*, a node of the off-chip ESD circuit **43***b*, and a power node of the testing interface circuit **333***b* through the through-silicon vias **11**. The power nodes of the inter-chip circuit **20***a*, the internal circuit **20***c*, the off-chip buffer **42***a* and the testing interface circuit **333***a* can be connected to the power nodes of the inter-chip circuit **20***b*, the internal circuit **20***d*, the off-chip buffer **42***b* and the testing interface circuit **333***b* through the middle one of the interconnecting structures **88**. The node of the off-chip ESD circuit **43***a* can be connected to the node of the off-chip ESD circuit **43***b* through the middle one of the interconnecting structures **88**.

[1237] Alternatively, the middle one of the interconnecting structures **88** can be used for a ground interconnect, such as ground plane, ground bus, ground trace or ground line, to connect with a ground node of the inter-chip circuit **20***a*, a ground node of the internal circuit **20***c*, a ground node of the off-chip buffer **42***a*, a node of the off-chip ESD circuit **43***a*, a ground node of the testing interface circuit **333***a*, a ground node of the inter-chip circuit **20***b*, a ground node of the internal circuit **20***d*, a ground node of the off-chip buffer **42***b*, a node of the off-chip ESD circuit **43***b*, and a ground node of the testing interface circuit **333***b* through the through-silicon vias **11**. The ground nodes of the inter-chip circuit **20***a*, the internal circuit **20***c*, the off-chip buffer **42***a* and the testing interface circuit **333***a* can be connected to the ground nodes of the inter-chip circuit **20***b*, the internal circuit **20***d*, the off-chip buffer **42***b* and the testing interface circuit **333***b* through the middle one of the interconnecting structures **88**. The node of the off-chip ESD circuit **43***a* can be connected to the node of the off-chip ESD circuit **43***b* through the middle one of the interconnecting structures **88**.

[1238] Next, referring to FIG. **46**F, with the step being illustrated with a reverse figure for simple explanation, a polymer layer **14** is formed on the metal layer **9**, on the insulating layer **3** and at sidewalls of the interconnecting structures **88** using a process including a spin-on coating process, a lamination process, a screen-printing process or a spraying process and including a curing process. Multiple openings **14***a* in the polymer layer **14** are over multiple regions of the metal layer **9** and expose them. The polymer layer **14** has a thickness larger than 2 micrometers, such as between 3 and 25 micrometers, and preferably between 5 and 15 micrometers, larger than that of each of the dielectric layers **30**, and larger than that of the passivation layer **5**. The material of the polymer layer **14** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[1239] Next, referring to FIG. **46**G, with the steps being illustrated with a reverse figure for simple explanation, an adhesion/barrier layer **16** having a thickness smaller than 1 micrometer, such as between 0.02 and 0.5 micrometers, and preferably between 0.1 and 0.2 micrometers, can be formed on the polymer layer **14** and on the regions of the metal layer **9** exposed by the openings **14***a* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **18** having a thickness smaller than 1 micrometer, such as between 0.05 and 0.5 micrometers, and preferably between 0.08 and 0.15 micrometers, can be formed on the adhesion/barrier layer **16** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The specification of the adhesion/barrier layer **16** and the seed layer **18** as shown in FIG. **46**G can be referred to as the specification of the adhesion/barrier layer **16** and the seed layer **18** as illustrated in FIG. **25**H, respectively. The process of forming the adhesion/barrier layer **16** and the seed layer **18** as shown in FIG. **46**G can be referred to as the process of forming the adhesion/barrier layer **16** and the seed layer **18** as illustrated in FIG. **25**H, respectively.

[1240] After forming the seed layer **18**, a photoresist layer **31**, such as positive-type photoresist layer or negtive-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 60 micrometers, is formed on the seed layer **18** by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **31** is patterned with the processes of exposure and development to form multiple openings **31***a* in the photoresist layer **31** exposing the seed layer **18**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **31** during the process of exposure.

[1241] Next, multiple metal bumps or pillars **27** are formed over the interconnecting structures **88**, on the seed layer **18** of any previously described material exposed by the openings **31***a*, and in the openings **31***a*. The metal bumps or pillars **27** may have a thickness larger than 5 micrometers, such as between 5 and 150 micrometers, and preferably between 10 and 100 micrometers, larger than that of the seed layer **18**, larger than that of the adhesion/barrier layer **16** and larger than that of each of the fine-line Metal layers **60**. The metal bumps or pillars **27** may have a width larger than 1 micrometer, such as between 5 and 150 micrometers, and preferably between 5 and 50 micrometers, and larger than that of each of the fine-line metal layers **60**. The material of the metal bumps or pillars **27** may include copper, gold, nickel, aluminum, silver, solder, platinum or a composite of the previously described materials. The specification of the metal bumps or pillars **27** as shown in FIG. **46**G can be referred to as the specification of the metal bump or pillar **27** as illustrated in FIG. **25**J. The process of forming the metal bumps or pillars **27** as shown in FIG. **46**G can be referred to as the process of forming the metal bump or pillar **27** as illustrated in FIG. **25**J.

[1242] Next, referring to FIG. **46**H, with the steps being illustrated with a reverse figure for simple explanation, the photoresist layer **31** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **31** could remain on the seed layer **18** not under the metal bumps or pillars **27**. Thereafter, the residuals can be removed from the seed layer **18** with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. Next, the seed layer **18** not under the metal bumps or pillars **27** is removed, and then the adhesion/barrier layer **16** not under the metal bumps or pillars **27** is removed. The process of removing the seed layer **18** not under the metal

bumps or pillars **27** as shown in FIG. **46**H can be referred to as the process of removing the seed layer **18** not under the metal bumps or pillars **27** as illustrated in FIG. **25**L, and the process of removing the adhesion/barrier layer **16** not under the metal bumps or pillars **27** as shown in FIG. **46**H can be referred to as the process of removing the adhesion/barrier layer **16** not under the metal bumps or pillars **27** as illustrated in FIG. **25**L.

[1243] In case the adhesion/barrier layer **16** not under the metal bumps or pillars **27** is removed using a wet etching process, multiple undercuts are formed under the metal bumps or pillars **27** overhanging the adhesion/barrier layer **16**. The adhesion/barrier layer **16** under the metal bump or pillar **27** has a first sidewall recessed from a second sidewall of the metal bump or pillar **27**, and a distance d**1** between the first sidewall and the second sidewall is between 0.1 and 2 micrometers.

[1244] Accordingly, as shown in FIG. **46**H, a bottom scheme **103** at the backside I a of the thinned silicon substrate **1** of the semiconductor wafer **10***c* can be formed with the insulating layer **3**, the polymer layer **14**, the adhesion/barrier layer **16**, the seed layer **18**, the metal bumps or pillars **27**, and the interconnecting structures **88** provided by the metal layers **4** and. The metal bumps or pillars **27** can be connected to the interconnecting structures **88** through the seed layer **18** and the adhesion/barrier layer **1**, and can be used to be bonded with the previously described substrate **301** or BGA substrate **302**. A pitch between neighboring two metal bumps or pillars **27** may be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers.

[1245] Referring to FIG. **46**I, after forming the metal bumps or pillars **27** shown in FIG. **46**H, the flux or insulating material **33** can be removed to expose the metal pads **600***b*, **600***s* and **600***t* exposed by the openings **50** in the passivation layer **5**. Next, referring to FIG. **46**J, a polymer layer **95** can be optionally formed on the passivation layer **5** of the semiconductor wafer **10***c*. Multiple openings **950** in the polymer layer **95** are over the metal pads **600***b*, **600***s* and **600***t* exposed by the openings **50** and expose them. The polymer layer **95** may have a thickness larger than 2 micrometers, such as between 3 and 50 micrometers, and preferably between 2 and 30 micrometers, larger than that of the passivation layer **5**, and larger than that of each of the dielectric layers **30**. The material of the polymer layer **95** may include benzocyclobutane (BCB), polyimide (PI), polybenzoxazole (PBO) or epoxy resin.

[1246] Next, referring to FIG. **46**K, an adhesion/barrier layer **32***s* having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, can be formed on the polymer layer **95** and on the metal pads **600***b*, **600***s* and **600***t* exposed by the openings **950** by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process, and then a seed layer **32***t* having a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, can be formed on the adhesion/barrier layer **32***s* by using a physical vapor deposition (PVD) process, such as sputtering process or evaporation process. The material of the adhesion/barrier layer **32***s* may include titanium, a titanium-tungsten alloy, titanium nitride, chromium, tantalum, tantalum nitride or a composite of the previously described materials, and the material of the seed layer **32***t* may include copper, nickel, aluminum, gold, silver, platinum or palladium.

[1247] When the adhesion/barrier layer **32***s* is formed by a suitable process or processes, e.g., by sputtering a titanium-containing layer, such as a single layer of titanium-tungsten alloy, titanium or titanium nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **95** and on the metal pads **600***b*, **600***s* and **600***t* exposed by the openings **950**, the seed layer **32***t* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the titanium-containing layer.

[1248] Alternatively, when the adhesion/barrier layer **32***s* is formed by a suitable process or processes, e.g., by sputtering a tantalum-containing layer, such as a single layer of tantalum or tantalum nitride, having a thickness smaller than 1 micrometer, such as between 1 and 300 nanometers, and preferably between 1.5 and 100 nanometers, on the polymer layer **95** and on the metal pads **600***b*, **600***s* and **600***t* exposed by the openings **950**, the seed layer **32***t* can be formed by a suitable process or processes, e.g., by sputtering a copper layer, a nickel layer, an aluminum layer, a gold layer, a silver layer, a platinum layer or a palladium layer with a thickness smaller than 1 micrometer, such as between 20 and 500 nanometers, and preferably between 35 and 300 nanometers, on the tantalum-containing layer.

[1249] After forming the seed layer **32***t*, a photoresist layer **71**, such as positive-type photoresist layer or negtive-type photoresist layer, having a thickness larger than 1 micrometer, such as between 1 and 60 micrometers, is formed on the seed layer **32***t* by a spin-on coating process, a lamination process, a screen-printing process or a spraying process. Next, the photoresist layer **71** is patterned with the processes of exposure and development to form multiple openings **710** in the photoresist layer **71** exposing the seed layer **32***t*, and the openings **710** are over the metal pads **600***b*, but over the metal pads **600***s* and **600***t* for testing is no opening in the photoresist layer **71**. A 1× stepper or 1× contact aligner can be used to expose the photoresist layer **71** during the process of exposure.

[1250] Next, a metal layer **34***s* is formed on the seed layer **32***t* of any previously described material exposed by the openings **710** and in the openings **710** by using an electroplating process, and then a solder layer **34***t* is formed on the metal layer **34***s* in the openings **710** by using an electroplating process. Both of the metal layer **34***s* and the solder layer **34***t* have a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, larger than that of the seed layer **32***t* and larger than that of the adhesion/barrier layer **32***s*. The material of the metal layer **34***s* includes copper and/or nickel, and the material of the solder layer **34***t* includes bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy. The solder layer **34***t* can be used to be bonded with the chip **313**.

[1251] For example, the metal layer **34***s* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of copper with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably

between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***t*, preferably the previously described copper layer **32***t*, exposed by the openings **710**, and the solder layer **34***t* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of copper by using an electroplating process.

[1252] Alternatively, the metal layer **34***s* can be formed by a suitable process or processes, e.g., by electroplating a single metal layer of nickel with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***t*, preferably the previously described copper or nickel layer **32***t*, exposed by the openings **710**, and the solder layer **34***t* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the single metal layer of nickel by using an electroplating process.

[1253] Alternatively, the metal layer **34***s* can be formed by a suitable process or processes, e.g., by electroplating a copper layer with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 2 and 20 micrometers or between 5 and 25 micrometers, on the seed layer **32***t*, preferably the previously described copper layer **32***t*, exposed by the openings **710**, and then electroplating a nickel layer with a thickness larger than 0.2 micrometers, such as between 0.3 and 6 micrometers, and preferably between 1 and 3 micrometers, on the electroplated copper layer. The solder layer **34***t* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, can be formed on the electroplated nickel layer of the metal layer **34***s* by using an electroplating process.

[1254] Next, referring to FIG. **46**L, the photoresist layer **71** is removed using an inorganic solution or using an organic solution with amide. Some residuals from the photoresist layer **71** could remain on the seed layer **32***t* not under the metal layer **34***s*. Thereafter, the residuals can be removed from the seed layer **32***t* with a plasma, such as an O_2 plasma or a plasma containing fluorine of below 200 PPM and oxygen. Next, the seed layer **32***t* not under the metal layer **34***s* is removed, and then the adhesion/barrier layer **32***s* not under the metal layer **34***s* is removed.

[1255] For example, the seed layer **32***t* not under the metal layer **34***s* and the adhesion/barrier layer **32***s* not under the metal layer **34***s* can be removed by a dry etching process, such as Ar sputtering etching process, reactive ion etching (RIE) process or ion milling process.

[1256] Alternatively, the seed layer **32***t* not under the metal layer **34***s* and the adhesion/barrier layer **32***s* not under the metal layer **34***s* can be removed by a wet etching process. When the seed layer **32***t* is a copper layer, it can be etched with a solution containing NH_4OH or with a solution containing H_2SO_4. When the adhesion/barrier layer **32***s* is a titanium-tungsten-alloy layer, it can be etched with a solution containing hydrogen peroxide or with a solution containing NH_4OH and hydrogen peroxide. When the adhesion/barrier layer **32***s* is a titanium layer, it can be etched with a solution containing hydrogen fluoride or with a solution containing NH_4OH and hydrogen peroxide.

[1257] In case the seed layer **32***t* not under the metal layer **34***s* is removed using a wet etching process, an undercut is formed under the metal layer **34***s* overhanging the seed layer **32***t*. The seed layer **32***t* under the metal layer **34***s* has a first sidewall recessed from a second sidewall of the metal layer **34***s*, and a distance between the first sidewall and the second sidewall is between 0.1 and 2 micrometers.

[1258] Accordingly, as shown in FIG. **46**L, multiple microbumps **317***f*, that is, metal bumps, provided by the adhesion/barrier layer **32***s*, the seed layer **32***t*, the metal layer **34***s* and the solder layer **34***t* are formed on the metal pads **600***b* exposed by the openings **50** and **950**, on the polymer layer **95**, and at the active side of the thinned silicon substrate **1**, and are used to be bonded with the chip **313**. Each of the microbumps **317***f* has a height larger than 2 micrometers, such as between 2 and 70 micrometers, and preferably between 5 and 50 micrometers, and a width or diameter larger than 3 micrometers, such as between 3 and 30 micrometers. A pitch P**3** between neighboring two microbumps **317***f* can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers. The inter-chip circuit **20***a* can be connected to one of the microbumps **317***f* through the metal interconnect line **640***b* and one of the openings **50**, and the inter-chip circuit **20***b* can be connected to another one of the microbumps **317***f* through the metal interconnect line **640***d* and another one of the openings **50**. There are no microbumps formed on the metal pads **600***s* and **600***t* exposed by the openings **50** and **950**, that is, the metal pads **600***s* and **600***t* are exposed by the openings **50** and **950** for testing the cache memory chip **311**.

[1259] Alternatively, referring to FIG. **46**M, the polymer layer **95** can be omitted, that is, the adhesion/barrier layer **32***s* can be formed on the passivation layer **5** and on the metal pads **600***b* exposed by the openings **50** in the passivation layer **5**. Accordingly, the microbumps **317***f* provided by the adhesion/barrier layer **32***s*, the seed layer **32***t*, the metal layer **34***s* and the solder layer **34***t* can be formed on the metal pads **600***b* exposed by the openings **50**, on the passivation layer **5**, and at the active side of the thinned silicon substrate **1**.

[1260] Alternatively, referring to FIG. **46**N, the steps shown in FIGS. **46**B-**46**I can be omitted, that is, after providing the semiconductor wafer **10***c* shown in FIG. **46**A, the steps shown in FIGS. **46**J-**46**L can be performed to form the polymer layer **95** and the microbumps **317***f*.

[1261] An IC structure **6***b* of the cache memory chip **311** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D contains the inter-chip circuits **20***a* and **20***b*, the internal circuits **20***c* and **20***d*, the off-chip circuit **40***a* including the off-chip buffer **42***a* and the off-chip ESD circuit **43***a*, the off-chip circuit **40***b* including the off-chip buffer **42***b* and the off-chip ESD circuit **43***b*, the dielectric layers **30**, the vias **30'**, the fine-line metal layers **60**, the via plugs **60'**, the testing interface circuits **333***a* and **333***b*, and the metal interconnect lines **640***a*, **640***b*, **640***c*, **640***d*, **640***i*, **640***j*, **640***k* and **640***m* as illustrated in FIG. **46**M or **46**N.

[1262] The processor unit **303** shown in FIGS. **37**A or **38**A can be formed using a process illustrated in FIGS. **47**A-**47**C. FIGS. **47**A-**47**C are cross-sectional views showing a process for bonding the chip **313**, bonded with the cache memory chip **321**, with the semiconductor wafer **10***c* finalized to be cut into

a plurality of the cache memory chip **311**. Referring to FIG. **47**A, the chip **313** of the stacked unit shown in FIG. **44**C is bonded with the semiconductor wafer **10***c* shown in FIG. **46**L by joining the solder layer **34***z* of the microbumps **317***d* of the chip **313** with the solder layer **34***t* of the microbumps **317***f* of the semiconductor wafer **10***c* using a reflow or heating process. During the reflow or heating process, the solder layer **34***z* and the solder layer **34***t* are melted into a solder layer **35***a* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, between the metal layers **34***y* and **34***s*. Accordingly, the previously described microbumps **317** provided by the adhesion/barrier layers **32***s* and **32***y*, the seed layers **32***t* and **32***z*, the metal layers **34***s* and **34***y* and the solder layer **35***a* can be formed between the metal pads **600***b* of the semiconductor wafer **10***c* and the metal pads **600***c* of the chip **313**. Each of the microbumps **317** has a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers. The microbumps **317** contact with the metal pads **600***b* and **600***c*, and the metal pads **600***b* can be connected to the metal pads **600***c* through the microbumps **317**. The pitch between neighboring two microbumps **317** can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers.

[1263] Next, referring to FIG. **47**B, the previously described underfill **107***d* without fillers, such as a polymer, is filled into a gap between the semiconductor wafer **10***c* and the chip **313**, and encloses the microbumps **317**. Next, the previously described heat spreader or heat sink **315** (not shown in FIGS. **47**B and **47**C) can be mounted onto the silicon substrate **1** of the cache memory chip **321** by adhering the heat spreader or heat sink **315** to the silicon substrate **1** of the cache memory chip **321** using the previously described film **319** of the glue material (not shown in FIGS. **47**B and **47**C).

[1264] Next, referring to FIG. **47**C, the semiconductor wafer **10***c* can be cut to singularize a plurality of the processor unit **303** including the cache memory chips **311** and **321**, the chip **313** and the heat spreader or heat sink **315**, and the chips **313** and **321** are connected to each other through the microbumps **317***a*, and the chips **311** and **313** are connected to each other thorough the microbumps **317**. Next, referring to FIG. **37**A or **38**A, the processor unit **303** shown in FIG. **47**C can be bonded with the substrate **301** or BGA substrate **302** by joining the metal bumps or pillars **27** of the cache memory chip **311** with multiple contact points of the substrate **301** or BGA substrate **302**, and then the previously described underfill **107***c* without fillers, such as a polymer, is filled into a gap between the cache memory chip **311** and the substrate **301** or BGA substrate **302**, and encloses the metal bumps or pillars **27**.

[1265] Accordingly, the off-chip buffer **42***a* and off-chip ESD circuit **43***a*, shown in FIG. **47**C, of the cache memory chip **311** can be connected to a signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through the left one of the interconnecting structures **88**, shown in FIG. **47**C, of the cache memory chip **311** and through the left one of the metal bumps or pillars **27**, also shown in FIG. **47**C, of the cache memory chip **311**. The off-chip buffer **42***b* and off-chip ESD circuit **43***b*, shown in FIG. **47**C, of the cache memory chip **311** can be connected to another signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through the right one of the interconnecting structures **88**, shown in FIG. **47**C, of the cache memory chip **311** and through the right one of the metal bumps or pillars **27**, also shown in FIG. **47**C, of the cache memory chip **311**.

[1266] The middle two of the metal bumps or pillars **27**, also shown in FIG. **47**C, of the cache memory chip **311** can be connected to a power interconnect, such as power plane, power bus, power trace or power line, of the substrate **301** or BGA substrate **302**, and the middle one of the interconnecting structures **88**, shown in FIG. **47**C, of the cache memory chip **311** can be connected to the power interconnect of the substrate **301** or BGA substrate **302** through the middle two of the metal bumps or pillars **27**.

[1267] Alternatively, the middle two of the metal bumps or pillars **27**, also shown in FIG. **47**C, of the cache memory chip **311** can be connected to a ground interconnect, such as ground plane, ground bus, ground trace or ground line, of the substrate **301** or BGA substrate **302**, and the middle one of the interconnecting structures **88**, shown in FIG. **47**C, of the cache memory chip **311** can be connected to the ground interconnect of the substrate **301** or BGA substrate **302** through the middle two of the metal bumps or pillars **27**.

[1268] The processor unit **303** shown in FIGS. **37**B or **38**B can be formed using a process illustrated in FIGS. **47**D-**47**F. FIGS. **47**D-**47**F are cross-sectional views showing a process for bonding the chip **313** with the semiconductor wafer **10***c* finalized to be cut into a plurality of the cache memory chip **311**. Referring to FIG. **47**D, the chip **313** shown in FIG. **420** is bonded with the semiconductor wafer **10***c* shown in FIG. **46**L by joining the solder layer **34***z* of the microbumps **317***d* of the chip **313** with the solder layer **34***t* of the microbumps **317***f* of the semiconductor wafer **10***c* using a reflow or heating process. During the reflow or heating process, the solder layer **34***z* and the solder layer **34***t* are melted into a solder layer **35***a* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, between the metal layers **34***y* and **34***s*. Accordingly, the previously described microbumps **317** provided by the adhesion/barrier layers **32***s* and **32***y*, the seed layers **32***t* and **32***z*, the metal layers **34***s* and **34***y* and the solder layer **35***a* can be formed between the metal pads **600***b* of the semiconductor wafer **10***c* and the metal pads **600***c* of the chip **313**. Each of the microbumps **317** has a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers. The microbumps **317** contact with the metal pads **600***b* and **600***c*, and the metal pads **600***b* can be connected to the metal pads **600***c* through the microbumps **317**. The pitch between neighboring two microbumps **317** can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers.

[1269] Next, referring to FIG. **47**E, the previously described underfill **107***d* without fillers, such as a polymer, is filled into a gap between the semiconductor wafer **10***c* and the chip **313**, and encloses the microbumps **317**, and then the previously described heat spreader or heat sink **315** is mounted onto the silicon substrate **1** of the chip **313** by adher-

ing the heat spreader or heat sink **315** to the silicon substrate **1** of the chip **313** using the previously described film **319** of the glue material.

[1270] Next, referring to FIG. **47**F, the semiconductor wafer **10***c* can be cut to singularize a plurality of the processor unit **303** including the cache memory chip **311**, the chip **313** and the heat spreader or heat sink **315**, and the chips **311** and **313** are connected to each other thorough the microbumps **317**. Next, referring to FIG. **37**B or **38**B, the processor unit **303** shown in FIG. **47**F can be bonded with the substrate **301** or BGA substrate **302** by joining the metal bumps or pillars **27** of the cache memory chip **311** with multiple contact points of the substrate **301** or BGA substrate **302**, and then the previously described underfill **107***c* without fillers, such as a polymer, is filled into a gap between the cache memory chip **311** and the substrate **301** or BGA substrate **302**, and encloses the metal bumps or pillars **27**.

[1271] Accordingly, the off-chip buffer **42***a* and off-chip ESD circuit **43***a,* shown in FIG. **47**F, of the cache memory chip **311** can be connected to a signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through the left one of the interconnecting structures **88**, shown in FIG. **47**F, of the cache memory chip **311** and through the left one of the metal bumps or pillars **27**, also shown in FIG. **47**F, of the cache memory chip **311**. The off-chip buffer **42***b* and off-chip ESD circuit **43***b,* shown in FIG. **47**F, of the cache memory chip **311** can be connected to another signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through the right one of the interconnecting structures **88**, shown in FIG. **47**F, of the cache memory chip **311** and through the right one of the metal bumps or pillars **27**, also shown in FIG. **47**F, of the cache memory chip **311**.

[1272] The middle two of the metal bumps or pillars **27**, also shown in FIG. **47**F, of the cache memory chip **311** can be connected to a power interconnect, such as power plane, power bus, power trace or power line, of the substrate **301** or BGA substrate **302**, and the middle one of the interconnecting structures **88**, shown in FIG. **47**F, of the cache memory chip **311** can be connected to the power interconnect of the substrate **301** or BGA substrate **302** through the middle two of the metal bumps or pillars **27**.

[1273] Alternatively, the middle two of the metal bumps or pillars **27**, also shown in FIG. **47**F, of the cache memory chip **311** can be connected to a ground interconnect, such as ground plane, ground bus, ground trace or ground line, of the substrate **301** or BGA substrate **302**, and the middle one of the interconnecting structures **88**, shown in FIG. **47**F, of the cache memory chip **311** can be connected to the ground interconnect of the substrate **301** or BGA substrate **302** through the middle two of the metal bumps or pillars **27**.

[1274] FIGS. **47**G-**47**I are cross-sectional views showing a process for bonding the chip **313** with the semiconductor wafer **10***c* finalized to be cut into a plurality of the cache memory chip **311** as shown in FIG. **37**C or **38**C.

[1275] The processor unit **303** shown in FIGS. **37**C or **38**C can be formed using a process illustrated in FIGS. **47**G-**47**I. FIGS. **47**G-**47**I are cross-sectional views showing a process for bonding the chip **313** with the semiconductor wafer **10***c* finalized to be cut into a plurality of the cache memory chip **311**. Referring to FIG. **47**G, the chip **313** shown in FIG. **42**O is bonded with the semiconductor wafer **10***c* shown in FIG. **46**N by joining the solder layer **34***z* of the microbumps **317***d* of the chip **313** with the solder layer **34***t* of the microbumps **317***f* of the semiconductor wafer **10***c* using a reflow or heating process. During the reflow or heating process, the solder layer **34***z* and the solder layer **34***t* are melted into a solder layer **35***a* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, between the metal layers **34***y* and **34***s*. Accordingly, the previously described microbumps **317** provided by the adhesion/barrier layers **32***s* and **32***y,* the seed layers **32***t* and **32***z,* the metal layers **34***s* and **34***y* and the solder layer **35***a* can be formed between the metal pads **600***b* of the semiconductor wafer **10***c* and the metal pads **600***c* of the chip **313**. Each of the microbumps **317** has a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers. The microbumps **317** contact with the metal pads **600***b* and **600***c,* and the metal pads **600***b* can be connected to the metal pads **600***c* through the microbumps **317**. The pitch between neighboring two microbumps **317** can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers.

[1276] Next, referring to FIG. **47**H, the previously described underfill **107***d* without fillers, such as a polymer, is filled into a gap between the semiconductor wafer **10***c* and the chip **313**, and encloses the microbumps **317**, and then the previously described heat spreader or heat sink **315** is mounted onto the silicon substrate **1** of the chip **313** by adhering the heat spreader or heat sink **315** to the silicon substrate **1** of the chip **313** using the previously described film **319** of the glue material.

[1277] Next, referring to FIG. **47**I, the semiconductor wafer **10***c* can be cut to singularize a plurality of the processor unit **303** including the cache memory chip **311**, the chip **313** and the heat spreader or heat sink **315**, and the chips **311** and **313** are connected to each other thorough the microbumps **317**.

[1278] Referring to FIG. **37**C or **38**C, after the step illustrated in FIG. **47**I, the processor unit **303** shown in FIG. **47**I can be mounted onto the substrate **301** or BGA substrate **302** by adhering the silicon substrate **1** of the cache memory chip **311** to the top side of the substrate **301** or BGA substrate **302** using the previously described glue material **319***a.* Next, the previously described wires **119***c,* such as gold wires or copper wires, can be bonded with the testing metal pads **600***t* and **600***s* of the cache memory chip **311** and with multiple contact points of the substrate **301** or BGA substrate **302** by using a wirebonding process. The testing metal pads **600***t* and **600***s* of the cache memory chip **311** can be connected to the contact points of the top side of the substrate **301** or BGA substrate **302** through the wirebonded wires **119***c*. Next, the previously described molding compound **323** is formed on the substrate **301** or BGA substrate **302**, encapsulating the wirebonded wires **119***c* and the chips **311** and **313**, and the heat spreader or heat sink **315** has the surface **315***a* uncovered by the molding compound **323** and substantially coplanar with the top surface **323***a* of the molding compound **323**.

[1279] Accordingly, the off-chip buffer **42***a* and off-chip ESD circuit **43***a,* shown in FIG. **47**I, of the cache memory chip **311** can be connected to a signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through one of the wirebonded wires **119***c*. The off-chip buffer **42***b* and off-chip ESD

circuit **43***b,* shown in FIG. **47**I, of the cache memory chip **311** can be connected to another signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through another one of the wirebonded wires **119***c.*

[1280] The processor unit **303** shown in FIGS. **37**D or **38**D can be formed using a process illustrated in FIGS. **47**J-**47**L. FIGS. **47**J-**47**L are cross-sectional views showing a process for bonding the chip **313**, bonded with the cache memory chip **321**, with the semiconductor wafer **10***c* finalized to be cut into a plurality of the cache memory chip **311**. Referring to FIG. **47**J, the chip **313** of the stacked unit shown in FIG. **44**C is bonded with the semiconductor wafer **10***c* shown 'in FIG. **46**N by joining the solder layer **34***z* of the microbumps **317***d* of the chip **313** with the solder layer **34***t* of the microbumps **317***f* of the semiconductor wafer **10***c* using a reflow or heating process. During the reflow or heating process, the solder layer **34***z* and the solder layer **34***t* are melted into a solder layer **35***a* including bismuth, indium, antimony, tin, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy with a thickness larger than 1 micrometer, such as between 1 and 30 micrometers, and preferably between 5 and 25 micrometers, between the metal layers **34***y* and **34***s*. Accordingly, the previously described microbumps **317** provided by the adhesion/barrier layers **32***s* and **32***y,* the seed layers **32***t* and **32***z,* the metal layers **34***s* and **34***y* and the solder layer **35***a* can be formed between the metal pads **600***b* of the semiconductor wafer **10***c* and the metal pads **600***c* of the chip **313**. Each of the microbumps **317** has a thickness larger than 5 micrometers, such as between 5 and 100 micrometers, and preferably between 10 and 60 micrometers. The microbumps **317** contact with the metal pads **600***b* and **600***c,* and the metal pads **600***b* can be connected to the metal pads **600***c* through the microbumps **317**. The pitch between neighboring two microbumps **317** can be smaller than 60 micrometers, and preferably smaller than 40 micrometers, such as between 5 and 40 micrometers, and preferably between 10 and 30 micrometers.

[1281] Next, referring to FIG. **47**K, the previously described underfill **107***d* without fillers, such as a polymer, is filled into a gap between the semiconductor wafer **10***c* and the chip **313**, and encloses the microbumps **317**, and then the previously described heat spreader or heat sink **315** (not shown in FIGS. **47**K and **47**L) is mounted onto the silicon substrate **1** of the cache memory chip **321** by adhering the heat spreader or heat sink **315** to the silicon substrate I of the cache memory chip **321** using the previously described film **319** of the glue material (not shown in FIGS. **47**K and **47**L).

[1282] Next, referring to FIG. **47**L, the semiconductor wafer **10***c* can be cut to singularize a plurality of the processor unit **303** including the cache memory chips **311** and **321**, the chip **313** and the heat spreader or heat sink **315**, and the chips **313** and **321** are connected to each other through the microbumps **317***a,* and the chips **311** and **313** are connected to each other through the microbumps **317**.

[1283] Referring to FIG. **37**D or **38**D, after the step illustrated in FIG. **47**L, the processor unit **303** shown in FIG. **47**L can be mounted onto the substrate **301** or BGA substrate **302** by adhering the silicon substrate **1** of the cache memory chip **311** to the top side of the substrate **301** or BGA substrate **302** using the previously described glue material **319***a*. Next, the previously described wires **119***c,* such as gold wires or copper wires, can be bonded with the testing metal pads **600***t* and **600***s* of the cache memory chip **311** and with multiple contact points of the substrate **301** or BGA substrate **302** by using a wirebonding process. The testing metal pads **600***t* and **600***s* of the cache memory chip **311** can be connected to the contact points of the top side of the substrate **301** or BGA substrate **302** through the wirebonded wires **119***c*. Next, the previously described molding compound **323** is formed on the substrate **301** or BGA substrate **302**, encapsulating the wirebonded wires **119***c* and the chips **311**, **313** and **321**, and the heat spreader or heat sink **315** has the surface **315***a* uncovered by the molding compound **323** and substantially coplanar with the top surface **323***a* of the molding compound **323**.

[1284] Accordingly, the off-chip buffer **42***a* and off-chip ESD circuit **43***a,* shown in FIG. **47**L, of the cache memory chip **311** can be connected to a signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through one of the wirebonded wires **119***c.* The off-chip buffer **42***b* and off-chip ESD circuit **43***b,* shown in FIG. **47**L, of the cache memory chip **311** can be connected to another signal interconnect, such as signal bus, signal trace, signal line or signal pad, of the substrate **301** or BGA substrate **302** through another one of the wirebonded wires **119***c.*

[1285] Alternatively, the stacked DRAM BGA package **139** can be replaced with another stacked DRAM package **1390** as shown in FIG. **48**A. The stacked DRAM package **1390** includes a ball-grid-array (BGA) substrate **1391**, multiple stacked DRAM chips **1392** over a top side of the BGA substrate **1391**, a control chip **1996** on the stacked DRAM chips **1392**, and the control chip **1996** can be used to determine which DRAM chip **1392** is activated to read or write date therefrom or therein, multiple solder balls **1393** containing bismuth, indium, a tin-lead alloy, a tin-silver alloy or a tin-silver-copper alloy on a bottom side of the BGA substrate **1391**, multiple wirebonded wires **1394**, such as gold wires, copper wires or aluminum wires, connecting one of the DRAM chips **1392** to another one of the DRAM chips **1392** or to the BGA substrate **1391**, and a molding compound **1395**, such as a polymer or an epoxy-based material, on the top side of the BGA substrate **1391** and on the DRAM chips **1392**, encapsulating the wirebonded wires **1394** and the DRAM chips **1392**. The stacked DRAM package **1390** can be provided on the substrate **301** shown in FIGS. **37**A, **37**B, **37**C and **37**D or on the BGA substrate **302** shown in FIGS. **38**A, **38**B, **38**C and **38**D, that is, the solder balls **1393** each have a top end bonded with the bottom side of the BGA substrate **1391** and a bottom end bonded with a top side of the substrate **301** shown in FIGS. **37**A, **37**B, **37**C and **37**D or with a top side of the BGA substrate **302** shown in FIGS. **38**A, **38**B, **38**C and **38**D, and accordingly the BGA substrate **1391** can be connected to the substrate **301** shown in FIGS. **37**A, **37**B, **37**C and **37**D through the solder balls **1393**, or to the BGA substrate **302** shown in FIGS. **38**A, **38**B, **38**C and **38**D through the solder balls **1393**. The BGA substrate **1391** may contain an epoxy-based polymer, such as BT epoxy.

[1286] FIGS. **48**C and **48**D show cross-sectional views of various types of a DRAM chip **1392** assembled or incorporated in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of F-F' of FIG. **48**B, and the redistribution circuit layer **1411** is made mainly of sputtered aluminum. FIGS. **48**E and **48**F shows cross-sectional views of various types of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of F-F' of FIG. **48**B, and the redistribution circuit layer **1411** is made mainly of electroplated copper or gold.

FIG. **48**G shows a top view of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A according to another embodiment. FIGS. **48**H and **48**I show cross-sectional views of various types of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of G-G' of FIG. **48**G, and the redistribution circuit layer **1411** is made mainly of sputtered aluminum. FIGS. **48**J and **48**K shows cross-sectional views of various types of a DRAM chip **1392** assembled in the stacked DRAM BGA package **1390** shown in FIG. **48**A along a cut line of G-G' of FIG. **48**G, and the redistribution circuit layer **1411** is made mainly of electroplated copper or gold. Referring to FIGS. **48**C-**48**F and **48**H-**48**K showing cross-sectional views of the DRAM chip **1392**, each of the DRAM chips **1392** may contain a silicon semiconductor substrate **1**, multiple off-chip drivers or receivers **42** each composed of multiple MOS devices **1397** each having diffusion portions, such as source **201** and drain **202** of the MOS devices, in the silicon semiconductor substrate **1** and a gate **203**, such as metal gate or poly gate, having a thickness between 0.002 and 0.2 micrometers on the silicon semiconductor substrate **1**, eight memory banks **1404** each including multiple memory cells and sense amplifiers connected to the memory cells, multiple metal layers **6** over the silicon semiconductor substrate **1**, and either one of the metal layers **6** can be sputtered aluminum having a thickness between 0.01 and 3 micrometers for one metal layer or damascene copper formed with electroplated copper, having a thickness between 0.01 and 3 micrometers for one metal layer, and a titanium, titanium-nitride, tantalum, or tantalum-nitride layer at a bottom and a sidewall of the electroplated copper, multiple dielectric or insulating layers **30** between the metal layers **6**, and each of the dielectric or insulating layers **30** can be silicon oxide having a thickness between 0.01 and 3 micrometers for the metal layers **6** made of sputtered aluminum or can be a composite containing a thin silicon-nitride or silicon oxynitride layer optionally containing carbon and having a thickness between 0.005 and 0.1 micrometers on the underlying damascene copper and a silicon-oxide layer optionally containing carbon and having a thickness between 0.05 and 3 micrometers on the thin silicon-nitride or silicon oxynitride layer for the metal layers **6** made of damascene copper, and a passivation layer **5** over the metal layers **6** and the dielectric or insulating layers **30**, and the passivation layer **5** can be a silicon-nitride or silicon-oxynitride layer having a thickness between 0.3 and 2 micrometers on the damascene copper of the top metal layer **6** or can be a composite containing a silicon-oxide layer having a thickness between 0.3 and 2 micrometers on the sputtered aluminum of the top metal layer **6** and a silicon-nitride or silicon-oxynitride layer having a thickness between 0.3 and 2 micrometers on the silicon-oxide layer. Openings **1407** in the passivation layer **5** are over multiple contact points **1408** of the top metal layer **6**, and the contact points **1408** are at bottoms of the openings **1407**. In case the contact point **1408** is connected to an off-chip driver **42**, the connect point **1408** is connected to drains of MOS devices **1397** of the off-chip driver **42**; in case the contact point **1408** is connected to an off-chip receiver **42**, the connect point **1408** is connected to gates of MOS devices **1397** of the off-chip receiver **42**. Except the above description, an element indicated by a same reference number as that indicating the element in other embodiments can be referenced to as the element other embodiments.

[1287] Referring to FIGS. **48**C, **48**D, **48**H and **48**I, each of the DRAM chips **1392** further contains a redistribution circuit layer **1411** on the passivation layer **5**, and the redistribution circuit layer **1411** contains an adhesion layer **1401**, such as titanium, titanium-tungsten alloy, titanium nitride, tantalum or tantalum nitride having a thickness between 0.002 and 0.05 micrometers, and a sputtered aluminum layer **1402** having a thickness between 0.7 and 5 micrometers, on the adhesion layer **1401**, and another passivation layer **1400** on the redistribution circuit layer **1411** and on the passivation layer **5**, and the passivation layer **1400** can be a composite containing a silicon-oxide layer having a thickness between 0.3 and 2 micrometers on the sputtered aluminum layer **1402** of the redistribution circuit layer **1411** and on the passivation layer **5** and a silicon-nitride or silicon-oxynitride layer having a thickness between 0.3 and 2 micrometers on the silicon-oxide layer. Multiple openings **1431** in the passivation layer **1400** are over contact points **1418**, configured for wirebonding, of the redistribution circuit layer **1411**, and the contact points **1418** are at bottoms of the openings **1431**.

[1288] Alternatively, referring to FIGS. **48**E, **48**F, **48**J and **48**K, each of the DRAM chips **1392** contains a polymer layer **1409**, such as polyimide or benzocyclobutene (BCB) having a thickness between 2 and 30 micrometers, on the passivation layer **5**, and openings **1410** in the polymer layer **1409** are over the contact points **1408** of the top metal layer **6**. The redistribution circuit layer **1411** can be formed on the polymer layer **1409**. In this case, the redistribution circuit layer **1411** contains an adhesion layer **1412**, such as titanium, titanium-tungsten alloy or titanium nitride having a thickness between 0.002 and 0.05 micrometers, a copper or gold seed layer **1413** having a thickness between 0.002 and 0.1 micrometers on the adhesion layer **1412**, and an electroplated copper or gold layer **1405** on the copper or gold seed layer **1413**. If the layer **1405** is electroplated copper, an optional nickel layer **1414** formed by a suitable process or processes, e.g., by an electroplating or electroless plating process can be provided on the electroplated copper layer **1405**, and an optional gold layer **1415** formed by a suitable process or processes, e.g., by an electroplating or electroless plating process can be provided on the nickel layer **1414**. Optionally, each of the DRAM chips **1392** may contain another polymer **1416**, such as polyimide or benzocyclobutene (BCB) having a thickness between 2 and 30 micrometers, on the redistribution circuit layer **1411** and on the polymer layer **1409**, and openings **1417** in the polymer layer **1416** are over the contact points **1418**, configured for wirebonding, of the redistribution circuit layer **1411**, and the contact points **1418** are at bottoms of the openings **1417**. Alternatively, the polymer layer **1409** can be omitted. The redistribution circuit layer **1411** can be provided directly on the passivation layer **5** and there is no polymer layer between the passivation layer **5** and the redistribution circuit layer **1411**. Alternatively, the polymer layer **1416** can be omitted and there is no polymer layer over the redistribution circuit layer **1411**.

[1289] FIGS. **48**B and **48**G show top perspective views of the DRAM chip **1392** according to two embodiments. Referring to FIG. **48**G, the contact points **1408** are arranged in a center line **1403** of the DRAM chip **1392** parallel with two opposite edges **1392***a* and **1392***b* of the DRAM chip. Alternatively, referring to FIG. **48**B, the contact points **1408** are arranged in two center lines **1421** and **1422** left and right away from the center line **1403** of the DRAM chip **1392**, respectively, and parallel with the two opposite edges **1392***a* and

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1392*b* of the DRAM chip. The region **1419** shown in FIGS. **48**B and **48**G enclosed by dot lines indicates a region of a top surface of the silicon semiconductor substrate **1**, in which the off-chip drivers or receivers **42** are provided, that is, there can be off-chip drivers or receivers **42** at a horizontal plane lower than that of the contact points **1408**, and each of the off-chip drivers or receivers **42** is connected to and positioned close to one of the contact points **1408**, as shown in FIGS. **48**C-**48**F and **48**H-**48**K. In a case, there is no off-chip driver or receiver vertically under the contact points **1408**, as shown in FIGS. **48**C, **48**E, **48**H and **48**J. For example, the off-chip driver or receiver **42**, as shown in FIGS. **48**C and **48**E, is at a horizontal plane lower than that of the contact point **1408** connected to the off-chip driver or receiver **42** and has a horizontal offset p from the center of the contact point **1408** by a range from **30** to 250 micrometers, with the contact points **1408** shown in FIG. **48**B arranged in two center lines **1421** and **1422** left and right away from the center line **1403** of the DRAM chip **1392**, respectively. Also, when the contact points **1408**, as shown in FIG. **48**G, are arranged in a center line **1403** of the DRAM chip **1392** parallel with two opposite edges **1392***a* and **1392***b* of the DRAM chip, the off-chip driver or receiver **42** at a horizontal plane lower than that of the contact point **1408** connected to the off-chip driver or receiver **42** may have a horizontal offset p from the center of the contact point **1408** by a range from 30 to 250 micrometers, as shown in FIGS. **48**H and **48**J.

[1290] In another case, there can be off-chip drivers or receivers **42** vertically under the contact points **1408**. As shown in FIG. **48**D and **48**F, the contact points **1408** can be vertically over and connected to the off-chip driver or receiver **42**, with the contact points **1408** shown in FIG. **48**B arranged in two center lines **1421** and **1422** left and right away from the center line **1403** of the DRAM chip **1392**, respectively, and a width or diameter D of the opening **1407** in the passivation layer **5** can be as small as possible, and, for example, can be between 0.2 and 20 micrometers, and preferably between 0.5 and 5 micrometers. Also, when the contact points **1408**, as shown in FIG. **48**G, are arranged in a center line **1403** of the DRAM chip **1392** parallel with two opposite edges **1392***a* and **1392***b* of the DRAM chip, the contact points **1408**, as shown in FIGS. **48**I and **48**K, can be vertically over and connected to the off-chip driver or receiver **42**, and a width or diameter D of the opening **1407** in the passivation layer **5** can be as small as possible, and, for example, can be between 0.2 and 20 micrometers, and preferably between 0.5 and 5 micrometers.

[1291] Referring to FIGS. **48**B and **48**G, the distance s between the left or right edge and the center line **1403** of the DRAM chip **1392** may range from 150 and 500 micrometers. Four of the eight memory banks **1404** are at the left side of the region **1419** and the other four of the eight memory banks **1404** are at the right side of the region **1419**. Referring to FIG. **48**G, the redistribution circuit layer **1411** can be patterned with multiple redistributed traces **1411***a* each connecting one of the contact points **1408** to one of the contact points **1418**, configured for wirebonding, arranged in a line close to the edge **1392***a*. Alternatively, referring to FIG. **48**B, the redistribution circuit layer **1411** can be patterned with multiple redistributed traces **1411***a* each connecting one of the contact points **1408** to one of the contact points **1418**, configured for wirebonding, arranged in two lines close to the edge **1392***a*.

[1292] A plurality of the previously described DRAM chip **1392** as illustrated in FIGS. **48**B-**48**K can be stacked. For example, there could be four, eight, sixteen or thirty two of DRAM chips **1392** are stacked, as described below:

[1293] Referring to FIG. **48**A, the bottommost DRAM chip **1392** can be mounted onto the BGA substrate **1391** by adhering the silicon semiconductor substrate **1** of the bottommost DRAM chip **1392** to the top side of the BGA substrate **1391** using a film **1420** of a glue material, such as a polymer or an epoxy-based material, with a thickness between 1 and 50 micrometers. The upper DRAM chip **1392** can be mounted onto the lower DRAM chip **1392** by adhering the silicon substrate **1** of the upper DRAM chip **1392** to the top side of the lower chip **1392** using another film **1420** of the glue material. The control chip **1996** can be mounted onto the topmost DRAM chip **1392** by adhering the control chip **1996** to the top side of the topmost DRAM chip **1392** using another film **1420** of the glue material. The upper DRAM chip **1392** has a right portion overhanging the lower DRAM chip **1392**, and the lower DRAM chip **1392** has a left portion not vertically under the upper DRAM chip **1392**. The upper DRAM chip **1392** has a left sidewall recessed from that of the lower DRAM chip **1392**. The wirebonded wires **1394** each may have an end bonded with the contact point **1418** of the upper DRAM chip **1392** or the contact point **1433** of the control chip **1996** and another end bonded with the contact point **1418** of the lower DRAM chip **1392** or with a metal pad **1399** of the BGA substrate **1391**. Particularly, in case the wirebonded wires **1394** are copper wires, the wirebonded wires **1394** each may have an end bonded with the electroplated copper layer **1405** of the upper DRAM chip **1392** or with copper of the contact point **1433** of the control chip **1996** and another end bonded with the electroplated copper layer **1405** of the lower DRAM chip **1392** or with copper of the metal pad **1399** of the BGA substrate **1391**. In case the wirebonded wires **1394** are gold wires, the wirebonded wires **1394** each may have an end bonded with the sputtered aluminum layer **1402**, the electroplated gold layer **1405** or the gold layer **1415** of the upper DRAM chip **1392** or with gold or aluminum of the contact point **1433** of the control chip **1996** and another end bonded with the sputtered aluminum layer **1402**, the electroplated gold layer **1405** or the gold layer **1415** of the lower DRAM chip **1392** or with gold of the metal pad **1399** of the BGA substrate **1391**.

[1294] The previously described module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D may include only one processor unit **303** on the substrate **301** or BGA substrate **302**. Alternatively, the module **137** may include a plurality of the processor unit **303** on the substrate **301** or BGA substrate **302**, and the way to assembly either one of the processor units **303** and to design the circuit of either one of the processor units **303** can be referenced to as either one of the ways to assembly the processor unit **303** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D and to design the circuit of the processor unit **303** shown in FIG. **39**A, **39**H, **39**I or **39**J.

[1295] For example, the module **137** may include three processor units **303** on the substrate **301** or BGA substrate **302**. The chip **313** in one of the processor units **303** can be a central-processing-unit (CPU) chip designed by x86 architecture or designed by non x86 architectures, the chip **313** in another one of the processor units **303** can be a graphics-processing-unit (GPU) chip, and the chip **313** in the other one of the processor units **303** can be a baseband chip.

[1296] Alternatively, the module **137** may include two processor units **303** on the substrate **301** or BGA substrate **302**.

The chip **313** in one of the processor units **303** can be a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, and the chip **313** in the other one of the processor units **303** can be a baseband chip.

[1297] Alternatively, the module **137** may include two processor units **303** on the substrate **301** or BGA substrate **302**. The chip **313** in one of the processor units **303** can be a system-on chip (SOC) including a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, and the chip **313** in the other one of the processor units **303** can be a graphics-processing-unit (GPU) chip.

[1298] The previously described module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D, the previously described chip-package module **118** shown in FIG. **36**A, the previously described chip-package module **118***a* shown in FIG. **36**B, the previously described chip-package module **118***b* shown in FIG. **36**C, the previously described chip-package module **118***c* shown in FIG. **36**D, the previously described semiconductor chips shown in FIGS. **29**A-**29**T, the previously described semiconductor chip cut from the previously described semiconductor wafer **10**, and the previously described chip package including the previously described semiconductor chip cut from the previously described semiconductor wafer **10** can be used for a telephone, a cordless phone, a mobile phone, a smart phone, a netbook computer, a notebook computer, a digital camera, a digital video camera, a digital picture frame, a personal digital assistant (PDA), a pocket personal computer, a portable personal computer, an electronic book, a digital book, a desktop computer, a tablet or slate computer, an automobile electronic product, a mobile internet device (MID), a mobile television, a projector, a mobile projector, a pico projector, a smart projector, a 3D video display, a 3D television (3D TV), a 3D video game player, a mobile computer device, a mobile compuphone (also called mobile phoneputer or mobile personal computer phone) which is a device or a system combining and providing functions of computers and phones, or a high performance and/or low power computer or server, for example, used for cloud computing.

[1299] When the module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D is used for the mobile compuphone, the memory size of the mass storage provided by the wirebonded stacked memory BGA package **138** is larger than 4 gigabytes, such as between 4 gigabytes and 1 trillion bytes, and the memory size of the main memory provided by the stacked DRAM BGA package **139** is larger than 100 megabytes, such as between 100 megabytes and 256 gigabytes, and preferably between 256 megabytes and 64 gigabytes.

[1300] When the module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D is used for the high performance and/or low power computer or server, the 3D video display, such as 3D television (3D TV), or the 3D video game player, and the high performance and/or low power computer or server, for example, can be used for cloud computing, the memory size of the mass storage provided by the wirebonded stacked memory BGA package **138** is larger than 4 gigabytes, such as between 4 gigabytes and 128 trillion bytes, and preferably between 64 gigabytes and 1 trillion bytes, and the memory size of the main memory provided by the stacked DRAM BGA package **139** is larger than 256 megabytes, such as between 256 megabytes and 1 trillion bytes, and preferably between 1 and 256 gigabytes.

[1301] When the module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D is used for the mobile compuphone, the cache memory chip **311** can be a dynamic-random-access-memory (DRAM) chip, a synchronous-dynamic-random-access-memory (SDRAM) chip or a statistic-random-access-memory (SRAM) chip, and the memory size of the cache memory chip **311** is between 10 megabytes and 32 gigabytes, and preferably between 100 megabytes and 4 gigabytes.

[1302] When the module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D is used for the high performance and/or low power computer or server, the 3D video display or the 3D video game player, the cache memory chip **311** can be a dynamic-random-access-memory (DRAM) chip, a statistic-random-access-memory (SRAM) chip or a synchronous-dynamic-random-access-memory (SDRAM) chip, and the memory size of the cache memory chip **311** is between 10 megabytes and 32 gigabytes, and preferably between 100 megabytes and 4 gigabytes.

[1303] The module **137** shown in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D, for example, can be provide for a high performance video display, especially for 3D video display, and can be connected to an in-situ (built-in) video display or in-situ (built-in) 3D video display, or can be connected to an external 3D video display, such as 3D TV or 3D video game player.

[1304] Alternatively, in FIG. **37**A, **37**B, **37**C, **37**D, **38**A, **38**B, **38**C or **38**D, the chip **313** may be a memory chip, such as synchronous-dynamic-random-access-memory (SDRAM) chip, statistic-random-access-memory (SRAM) chip or dynamic-random-access-memory (DRAM) chip, while the chip **311** may be a central-processing-unit (CPU) chip designed by x86 architecture, a central-processing-unit (CPU) chip designed by non x86 architectures, such as ARM, Strong ARM or MIPs, a baseband chip, a graphics-processing-unit (GPU) chip, a digital-signal-processing (DSP) chip, a wireless local area network (WLAN) chip, a global-positioning-system (GPS) chip, a bluetooth chip, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any baseband circuit block, a system-on chip (SOC) including a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any graphics-processing-unit (GPU) circuit block, a system-on chip (SOC) including a baseband circuit block, a graphics-processing-unit (GPU) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not including any wireless local area network (WLAN) circuit block, a system-on chip (SOC) including a baseband circuit block and a wireless local area network (WLAN) circuit block, but not including any graphics-processing-unit (GPU) circuit block and any central-processing-unit (CPU) circuit block, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block and a wireless

local area network (WLAN) circuit block, but not including any baseband circuit block and any central-processing-unit (CPU) circuit block, a system-on chip (SOC) including a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, or a chip including a central-processing-unit (CPU) circuit block, a bluetooth circuit block, a global-positioning-system (GPS) circuit block, a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, and/or a wireless local area network (WLAN) circuit block. It is noted that this architechture can be also designed with the circuits illustrated in FIG. **39**A, **39**H, **39**I or **39**J.

[1305] Accordingly, aspects and embodiments of the present disclosure can provide benefits and advantages over previous techniques

[1306] The components, steps, features, benefits and advantages that have been discussed are merely illustrative. None of them, nor the discussions relating to them, are intended to limit the scope of protection in any way. Numerous other embodiments are also contemplated. These include embodiments that have fewer, additional, and/or different components, steps, features, benefits and advantages. These also include embodiments in which the components and/or steps are arranged and/or ordered differently.

[1307] In reading the present disclosure, one skilled in the art will appreciate that embodiments of the present disclosure can be implemented in or facilitated by computer hardware, software, firmware, or any combinations of such, and over one or more networks. Suitable software can include computer-readable or machine-readable instructions for performing methods and techniques (and portions thereof) of designing and/or controlling the fabrication of chip structures in accordance with the present disclosure. Any suitable software language (machine-dependent or machine-independent) may be utilized. Moreover, embodiments of the present disclosure can be included in or carried by various signals, e.g., as transmitted over a wireless RF or IR communications link or downloaded from the Internet.

[1308] Unless otherwise stated, all measurements, values, ratings, positions, magnitudes, sizes, and other specifications that are set forth in this specification, including in the claims that follow, are approximate or of a nominal value, and not necessarily exact; they are intended to have a reasonable range that is consistent with the functions to which they relate and with what is customary in the art to which they pertain.

[1309] All articles, patents, patent applications, and other publications which have been cited in this disclosure are hereby incorporated herein by reference.

[1310] Nothing that has been stated or illustrated is intended or should be interpreted to cause a dedication of any component, step, feature, object, benefit, advantage, or equivalent to the public, regardless of whether it is recited in the claims.

[1311] The scope of protection is limited solely by the claims. That scope is intended and should be interpreted to be as broad as is consistent with the ordinary meaning of the language that is used in the claims when interpreted in light of this specification and the prosecution history that follows and to encompass all structural and functional equivalents.

What is claimed is:

1. A module comprising:

a substrate;

a processor unit on said substrate, wherein said processor unit comprises a first cache memory chip over said substrate and a processor chip over said first cache memory chip, wherein said first cache memory chip is connected to said processor chip through a plurality of microbumps between said first cache memory chip and said processor chip, wherein a pitch between a neighboring two of said plurality of microbumps is smaller than 60 micrometers;

a mass storage on said substrate, wherein said mass storage comprises a first memory chip over said substrate and a second memory chip over said first memory chip, wherein said first memory chip is connected to said second memory chip through at least one first wirebonded wire;

a main memory on said substrate, wherein said main memory comprises a first dynamic-random-access-memory chip over said substrate and a second dynamic-random-access-memory chip over said first dynamic-random-access-memory chip; and

a connector connected to said substrate.

2. The module of claim **1**, wherein the module is implemented in a computer, a mobile phone, a mobile compuphone, a camera, an electronic book, a digital picture frame, an automobile electronic product, a 3D video display, a 3D television, a 3D video game player, a projector, or a server used for cloud computing.

3. The module of claim **1**, wherein said processor chip comprises a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, a graphics-processing-unit (GPU) circuit block, a baseband circuit block, a digital-signal-processing (DSP) circuit block, or a wireless local area network (WLAN) circuit block.

4. The module of claim **1**, wherein said processor chip comprises a central-processing-unit (CPU) chip designed by x86 architecture or by non x86 architectures.

5. The module of claim **1**, wherein said processor chip comprises a system-on chip (SOC) comprising a baseband circuit block, a wireless local area network (WLAN) circuit block and a central-processing-unit (CPU) circuit block designed by x86 architecture or by non x86 architectures, but not comprising any graphics-processing-unit (GPU) circuit block.

6. The module of claim **1**, wherein said first cache memory chip comprises a dynamic-random-access-memory (DRAM) chip, a synchronous-dynamic-random-access-memory (SDRAM) chip, or a static-random-access-memory (SRAM) chip.

7. The module of claim **1**, wherein said first cache memory chip has a memory size between 10 megabytes and 32 gigabytes.

8. The module of claim **1**, wherein said first cache memory chip is connected to said substrate through at least one second wirebonded wire.

9. The module of claim **1**, wherein said first cache memory chip comprises a silicon substrate, a plurality of through-silicon vias in said silicon substrate, a bottom scheme at a backside of said silicon substrate and in said plurality of through-silicon vias, a first dielectric layer over a top side of said silicon substrate, a first metal layer over said first dielectric layer, a second dielectric layer over said first metal layer, a second metal layer over said second dielectric layer, and a

passivation layer over said top side of said silicon substrate, over said first and second dielectric layers and over said first and second metal layers, wherein each of a plurality of openings in said passivation layer is over a respective one of a plurality of contact points of said second metal layer, and said plurality of contact points is at bottoms of said plurality of openings, wherein said plurality of microbumps is connected to said plurality of contact points through said plurality of openings, wherein said bottom scheme comprises a metal bump between said silicon substrate and said substrate, wherein said first cache memory chip is connected to said substrate through said metal bump.

10. The module of claim **1**, wherein said first memory chip comprises a flash memory chip or a dynamic-random-access-memory (DRAM) chip.

11. The module of claim **1**, wherein said processor unit further comprises a second cache memory chip over said processor chip, wherein said second cache memory chip is connected to said processor chip.

12. The module of claim **1**, wherein said second memory chip has a right portion overhanging said first memory chip, and said first memory chip has a left portion not vertically under said second memory chip, wherein said second memory chip has a left sidewall recessed from that of said first memory chip.

13. The module of claim **1** further comprising a radio frequency (RF) module on said substrate.

14. The module of claim **1**, wherein said first dynamic-random-access-memory chip comprises a first silicon substrate, a first dielectric layer over said first silicon substrate, a first metal layer over said first dielectric layer, a second dielectric layer over said first metal layer, a second metal layer over said second dielectric layer, and a first passivation layer over said first silicon substrate, over said first and second dielectric layers and over said first and second metal layers, wherein each of a plurality of openings in said first passivation layer is over a respective one of a plurality of contact points of said second metal layer, and said plurality of contact points is at bottoms of said plurality of openings, wherein said second dynamic-random-access-memory chip comprises a second silicon substrate, a plurality of through-silicon vias in said second silicon substrate, a bottom scheme at a backside of said second silicon substrate and in said plurality of through-silicon vias, a third dielectric layer over a top side of said second silicon substrate, a third metal layer over said third dielectric layer, a fourth dielectric layer over said third metal layer, a fourth metal layer over said fourth dielectric layer, and a second passivation layer over said top side of said second silicon substrate, over said third and fourth dielectric layers and over said third and fourth metal layers, wherein said bottom scheme comprises a metal bump between said second silicon substrate and said first dynamic-random-access-memory chip, wherein said metal bump is connected to one of said plurality of contact points through one of said plurality of openings, wherein said second dynamic-random-access-memory chip is connected to said first dynamic-random-access-memory chip through said metal bump.

15. The module of claim **1**, wherein said connector is used for connecting to a charger, a game player, a display, or a television.

16. The module of claim **1**, wherein said connector comprises a universal serial bus (USB), a high-definition multimedia interface (HDMI), a DisplayPort, an IEEE 1394, or an optical connector.

17. The module of claim **1**, wherein said first cache memory chip comprises a first metal pad, a second metal pad, a testing interface circuit having a first node connected to said first metal pad, a first inter-chip buffer connected to said first metal pad and to said first node of said testing interface circuit, an off-chip buffer having a first node connected to a second node of said testing interface circuit and a second node connected to said second metal pad, and an off-chip electro static discharge (ESD) circuit connected to said second node of said off-chip buffer and to said second metal pad, wherein one of said plurality of microbumps is on said first metal pad, wherein said one of said plurality of microbumps is connected to said first inter-chip buffer and to said first node of said testing interface circuit through said first metal pad, wherein said second metal pad is not connected upwards to said processor chip through any microbump between said first cache memory chip and said processor chip.

18. The module of claim **17**, wherein said off-chip buffer comprises a first NMOS transistor, and said first inter-chip buffer comprises a second NMOS transistor, wherein a ratio of a physical channel width to a physical channel length of said first NMOS transistor is greater than a ratio of a physical channel width to a physical channel length of said second NMOS transistor by more than 3 times.

19. The module of claim **17**, wherein said processor chip comprises a third metal pad and a second inter-chip buffer connected to said third metal pad, wherein said one of said plurality of microbumps is between said first and third metal pads, wherein said one of said plurality of microbumps is connected to said second inter-chip buffer through said third metal pad, wherein said first inter-chip buffer is connected to said second inter-chip buffer through, in sequence, said first metal pad, said one of said plurality of microbumps, and said third metal pad.

20. The module of claim **19**, wherein there is no electro static discharge (ESD) circuit connected to a path between said first inter-chip buffer and said second inter-chip buffer.

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